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SURFACE MOUNTED SEMICONDUCTORS

SELECTION GUIDE

GENERAL PURPOSE TRANSISTORS in SOT-23/SOT-89*/SOT-143**

type	RATINGS V_{CBO} V	V_{CEO} V	I_C mA	P_{tot} mW	h_{FE} min./max.	at I_C/V_{CE} mA/V	V_{CEsat} max. V	at I_C/I_B mA	f_T typ. MHz	page
P-N-P										
BC807	45	45	500	310	100/600	100/1	0,70	500/50	100	149
BC808	25	25	500	310						149
BC856	65	65	100	200	75/475	2/5	0,30	10/0,5	150	183
BC857	45	45	100	200	75/475	2/5	0,30	10/0,5	150	183
BC858	30	30	100	200	75/800	2/5	0,30	10/0,5	150	183
BC869*	20	20	1000	1000	85/375	500/1	0,50	1000/100	60	207
BCV26	40	30	300	350	> 20 000	100/5	1,0	100/0,1	220	241
BCV62**	30	30	100	200	100/800	2/5	0,65	100/5	150	249
BCV63**	30	30	100	300	100/900	2/5	0,65	100/5	200	253
BCV64**	30	30	100	300	100/900	2/5	0,30	100/0,5	200	257
BCV65**	30	30	100	300	75/800	2/5	0,30	10/0,5	100	261
BCW29	32	32	100	350	120/260	2/5	0,30	10/0,5	150	269
BCW30					215/500					269
BCW61A	32	32	200	150	120/220	2/5	0,25	10/0,25	180	289
BCW61B					180/310					289
BCW61C					250/460					289
BCW61D					380/630					289
BCW69	50	45	100	350	120/260	2/5	0,30	10/0,5	150	293
BCW70					120/500					293
BCW89	80	60			120/260					313
BCX17	50	45	500	425	100/600	100/1	0,62	500/50	100	317
BCX18	30	25								317
BCX51*	45	45	1000	1000	40/250	150/2	0,50	500/50	50	329
BCX52*	60	60			40/160					329
BCX53*	100	80			40/160					329
BCX71G	45	45	200	150	120/220	2/5	0,25	10/0,25	180	341
BCX71H	45	45	200	150	180/310					341
BCX71J	45	45	200	150	250/460					341
BCX71K	45	45	200	150	380/630					341
PMBTA55	60	60	500	300	50	10/1	0,25	100/10	50	769
PMBTA56	80	80	500	300	50	10/1	0,25	100/10	50	769
PMBTA63	30	30	500	300	5,000	10/5	1,5	100/0,1	125	771
PMBTA64	30	30	500	300	5,000	10/5	1,5	100/0,1	125	771

* Types in SOT-89 package.
** Types in SOT-143 package.

GENERAL PURPOSE TRANSISTORS in SOT-23/SOT-89*/SOT-143**

type	RATINGS				h_{FE}		V_{CEsat}		f_T	page
	V_{CBO} V	V_{CEO} V	I_C mA	P_{tot} mW	min./max.	at I_C/V_{CE} mA/V	max. V	at I_C/I_B mA	typ. MHz	
N-P-N										
BC817	45	45	500	310	100/600	100/1	0,70	500/50	200	155
BC818	25	25	500	310						155
BC846	65	65	100	200	220/800	2/5	0,25	10/0,5	300	161
BC847	45	45	100	200						161
BC848	30	30	100	200						161
BC868*	20	20	1000	1000	85/375	500/1	0,50	1000/100	60	201
BCV27	40	30	300	350	> 20 000	100/5	1,0	100/0,1	220	243
BCV61**	30	30	100	200	100/800	2/5	0,60	100/5	300	245
BCV71	80	60	100	350	110/220	2/5	0,25	10/0,5	300	265
BCV72					200/450					265
BCW31	32	32	100	350	110/220	2/5	0,25	10/0,5	300	277
BCW32					200/450					277
BCW33					420/800					277
BCW60A	32	32	200	150	120/220	2/5	0,35	10/0,25	250	285
BCW60B					180/310					285
BCW60C					250/460					285
BCW60D					380/630					285
BCW71	50	45	100	350	110/220	2/5	0,25	10/0,5	300	301
BCW72					220/450					301
BCW81					450/800					309
BCX19	50	45	500	425	100/600	100/1	0,62	500/50	200	323
BCX20	30	25								323
BCX54*	45	45	1000	1000	45/250	150/2	0,50	500/50	130	333
BCX55*	60	60			40/160					333
BCX56*	100	80			40/160					333
BCX70G	45	45	200	150	120/220	2/5	0,35	10/0,25	250	337
BCX70H					180/310					337
BCX70J					250/460					337
BCX70K					380/630					337

* Types in SOT-89 package.
** Types in SOT-143 package.

GENERAL PURPOSE TRANSISTORS in SOT-23/SOT-89*/SOT-143**

type	RATINGS V_{CBO} V	V_{CEO} V	I_C mA	P_{tot} mW	h_{FE} min./max.	at I_C/V_{CE} mA/V	V_{CEsat} max. V	at I_C/I_B mA	f_T typ. MHz	page
N-P-N										
PMBT6428	60	50	200	350	250/600		0,2	10/0,5	300	757
PMBT6429	55	45	200	350	500/1250		0,2	10/0,5	300	757
PMBTA05	60	60	500	300	50	10/1	0,25	100/10	100	761
PMBTA06	80	80	500	300	50	10/1	0,25	100/10	100	761
PMBTA13	30	30	300	300	5,000	10/5	1,5	100/0,1	125	763
PMBTA14	30	30	300	300	10,000	10/5	1,5	100/0,1	125	763

HIGH-FREQUENCY TRANSISTORS in SOT-23

type	RATINGS V_{CBO} V	V_{CEO} V	I_C mA	P_{tot} mW	h_{FE} min./max.	at I_C/V_{CE} mA/V	F typ. dB	at f MHz	f_T typ. MHz	C_{re} typ. pF	page
P-N-P											
BF536	30	30	25	200	25/–	1/10	5	200	350	–	351
BF550	40	40	25	200	50/–	1/10	2	0,1	325	0,5	355
BF569	40	35	30	200	25/–	3/10	4,5	800	900	0,33	359
BF579	20	20	25	150	20/–	10/10	4,5	800	1350	0,46	367
BF660	40	30	25	200	30/–	3/10	–	–	650	0,65	379
BF767	30	30	20	200	15/–	3/10	4	800	900	0,3	383
BF824	30	30	25	300	–	–	3	100	450	0,1	399
N-P-N											
BF570	40	15	100	300	> 40	10/1	–	–	> 490	1,6	363
BF840	40	40	25	300					380	0,3	405
BF841	40	40	25	300					380	0,3	405
BFS18	30	20	30	250	35/125	1/10	4	100	200	0,85	525
BFS19	30	20	30	250	65/225	1/10	4	100	260	0,85	525
BFS20	30	20	25	250	40/85	7/10	–	–	450	0,35	531

* Types in SOT-89 package.
** Types in SOT-143 package.

BROAD-BAND TRANSISTORS in SOT-23/SOT-89*/SOT-143**

type	RATINGS V_{CBO} V	V_{CEO} V	I_C mA	P_{tot} mW	h_{FE} min./max.	at I_C/V_{CE} mA/V	d_{im} typ. dB	at f MHz	f_T typ. GHz	C_{re} typ. pF	page
P-N-P											
BFT92	20	15	25	200	20/–	14/10	60	493,25	5	0,7	553
BFT93	15	12	35	200	20/	30/5	60	493,25	5	1,0	559
N-P-N											
BFG67**	20	10	50	300	20/–	15/5	3	2000	7,5	0,5	433
BFQ17*	40	25	150	1000	25/–	150/6		–	1,2	1,9	437
BFQ18A	25	15	150	1000	25/–	100/10	60	793,25	3,6	1,2	441
BFQ19*	20	15	75	500	25/–	75/10		–	5,0	1,3	445
BFQ67	20	10	50	180	100	15/5	3	2000	7,5	0,5	449
BFR53	18	10	50	250	25/–	50/5	60	217,0	2,0	0,9	463
BFR92	20	15	25	200	25/–	14/10	60	493,25	5,0	0,7	473
BFR92A	20	15	25	200	40/–	14/10	60	793,25	5,0	0,35	483
BFR93	15	12	35	200	25/–	30/5	60	493,25	5,0	0,8	495
BFR93A	15	12	35	250	40/–	30/5	60	793,25	5,0	0,6	505
BFS17	25	15	25	250	20/150	2/1	45	217	1,3	0,65	519
BFT25	8	5	2,5	50	20/–	1/1		–	2,3	0,45	537

SWITCHING TRANSISTORS in SOT-23/SOT-89*

type	RATINGS V_{CBO} V	V_{CEO} V	I_C mA	P_{tot} mW	h_{FE} min./max.	at I_C/V_{CE} mA/V	V_{CEsat} max. V	at I_C/I_B mA/mA	t (max.) on/off ns	at I_C/I_B mA	page
P-N-P											
BSR12	15	15	100	250	30/120	50/1	0,45	100/10	20/30	30/3	581
BSR15	60	40	600	425	100/300	150/10	1,6	500/50	45/100	150/15	593
BSR16	60	60									593
BSR18	40	40	200	250	50/150	10/1	0,40	50/5	70/250	10/1	603
BSR18A	40	40	200	250	100/300	10/1	0,4	50/5	70/300	10/1	603
BSR20	130	120	600	350	40/180	10/5	0,5	50/5			611
BSR20A	160	150	600	350	60/240	10/5	0,5	50/5			611
BSR30*	70	60	1000	1000	40/120	100/5	0,5	500/50	500/650	100/5	615
BSR31*	70	60			100/300						615
BSR32*	90	80			40/120						615
BSR33*	90	80			100/300						615
BSS63	110	100	100	350	30/–	25/1	0,25	25/2,5	–	–	627
BST60*	60	45	500	1000	1000/–	150/10	1,3	500/0,5	400/1500	500/0,5	653
BST61*	80	60									653
BST62*	100	80									653
PMBT3906	40	40	200	300	100/300	10/1	0,25	10/1	35/225	10/1	753
PXT3906	40	40	200	1000	100/300	10/1	0,25	10/1	35/225	10/1	783

* Types in SOT-89 package are denoted by an asterisk (*).
** Types in SOT-143 package are denoted by two asterisks (**).

SWITCHING TRANSISTORS in SOT-23/SOT-89*

type	RATINGS V_{CBO} V	V_{CEO} V	I_C mA	P_{tot} mW	h_{FE} min./max.	at I_C/V_{CE} mA/V	V_{CEsat} max. V	at I_C/I_B mA/mA	t (max.) on/off ns	at I_C/I_B mA	page
N-P-N											
BSR13	60	30	800	425	100/300	150/10	1,6	500/50	35/285	150/–	587
BSR14	75	40					1,0				587
BSR17	60	40	200	350	50/150	10/1	0,3	50/5	70/225	10/1	599
BSR17A	60	40	200	350	100/300	10/1	0,3	50/5	70/250	10/1	599
BSR19	160	140	600	350	60/250	10/5	0,25	50/5			607
BSR19A	180	160	600	350	80/250	10/5	0,20	50/5			607
BSR40*	70	60	1000	1000	40/120	100/5	0,5	500/50	250/1000	100/5	619
BSR41*					100/300						619
BSR42*	90	80	1000	1000	40/120	100/5	0,5	500/50	250/1000	100/5	619
BSR43*					100/300						619
BSS64	120	80	100	350	20/80	10/1	0,2	50/15	/1000	15/1	633
BST50*	60	45	500	1000	1000/–	150/10	1,3	500/50	400/1500	500/0,5	649
BST51*	80	60	500	1000							649
BST52*	100	80	500	1000							649
BSV52	20	12	100	250	40/120	10/1	0,2	50/5	12/18	10/3	681
PMBT3903	60	40	200	300	50/150	10/1	0,3	50/5	35/175	10,1	749
PMBT3904	60	40	200	300	100/300	10/1	0,3	50/5	35/200	10,1	749
PXT3904*	60	40	200	1000	100/300						779

LOW-NOISE TRANSISTORS in SOT-23 (F < 4 dB at f = 1 kHz; B = 200 Hz)

type	RATINGS V_{CBO} V	V_{CEO} V	I_C mA	P_{tot} mW	h_{FE} min./max.	at I_C/V_{CE} mA/V	V_{CEsat} max. V	at I_C/I_B mA	f_T typ. MHz	page
P-N-P										
BC859	30	30	100	200	125/800	2/5	0,3	10/0,5	150	191
BC860	45	45	100	200	125/800	2/5	0,3	10/0,5	150	191
BCF29	32	32	100	350	120/260	2/5	0,3	10/0,5	150	213
BCF30	32	32	100	350	215/500	2/5	0,3	10/0,5	150	213
BCF70	50	45	100	350	215/500	2/5	0,3	10/0,5	150	229
N-P-N										
BC849	30	30	100	200	450/800	2/5	0,25	10/0,5	300	171
BC850	45	45	100	200						171
BCF32	32	32	100	350	200/450	2/5	0,25	10/0,5	300	221
BCF33	32	32	100	350	420/800	2/5	0,25	10/0,5	300	221
BCF81	50	45	100	350	420/800	2/5	0,25	10/0,5	300	237

* Types in SOT-89 package are denoted by an asterisk (*).

HIGH-VOLTAGE TRANSISTORS in SOT-23/SOT-89*

type	RATINGS V_{CBO} V	V_{CEO} V	I_C mA	P_{tot} mW	h_{FE} min./max.	at I_C/V_{CE} mA/V	V_{CEsat} max. V	at I_C/I_B mA	f_T min. MHz	page
P-N-P										
BF621*	300	–	20	1000	50/–	25/20	0,8	30/5	60	375
BF623*	250	250	20	1000	50/–	25/20	0,8	30/5	60	375
BF821	300	–	50	310	50/–	25/20	0,8	30/5	60	393
BF823	250	250	50	310	50/–	25/20	0,8	30/5	60	393
BST15*	200	200	1000	1000	30/150	50/10	2,5	50/5	15	641
BST16*	350	300	1000	1000	30/120	50/10	2,0	50/5	15	641
PMBTA92	300	300	500	300	40/–	10/10	0,5	20/2	50	773
PMBTA93	200	200	500	300	40/–	10/10	0,5	20/2	50	773
N-P-N										
BF620*	300	–	20	1000	50/–	25/20	0,6	30/5	60	371
BF622*	250	250	20	1000	50/–	25/20	0,6	30/5	60	371
BF820	300	–	50	310	50/–	25/20	0,6	30/5	60	387
BF822	250	250	50	310	50/–	25/20	0,6	30/5	60	387
BST39*	350	300	1000	1000	40/160	20/10	0,5	50/4	70	645
BST40*	350	250	1000	1000	40/160	20/10	0,5	50/4	70	645
PMBTA42	300	300	500	310	40/–	30/10	0,5	20/2	50	765
PMBTA43	200	200	500	310	40/–	30/10	0,5	20/2	50	765

* Types in SOT-89 package are denoted by an asterisk (*).

FIELD-EFFECT TRANSISTOR in SOT-23/SOT-143*/SOT-89**

type	RATINGS $\pm V_{DS}$ V	$-V_{GSO}$ V	I_D mA	P_{tot} mW	$-I_{GSS}$ max. nA	I_{DSS} min./max. mA	$-V_{(P)GS}$ max. V	$\|y_{fs}\|$ min. mS	C_{re} max. pF	V_n max. μV	page
BF510	80	–	30	300	10	0,7/3,0	0,8	2,5	0,4	–	345
BF511						2,5/7,0	1,5	4			345
BF512						6/12	2,2	6			345
BF513						10/18	3	7			345
BF989*	20	–	20	200	50	2/20	2,7	9,5	0,025	–	407
BF990*	18	–	30	200	25	–	1,3	17	0,025	–	409
BF991*	20	–	20	200	50	4/25	2,5	10	0,020	–	413
BF992*	20	–	40	200	25	–	1,3	20	0,04	–	415
BF994*	20	–	30	200	50	2/20	2,5	15	0,025	–	417
BF994S*	20	–	50	300	50	4/20	2,5	15	0,025	–	421
BF996*	20	–	30	200	50	2/20	2,5	15	0,025	–	423
BF996S*	20	–	30	300	50	4/20	2,5	15	0,025	–	427
BF997*	20	–	30	300	10	2/20	2,5	15	0,025	–	429
BFR30	25	25	10	250	0,2	4/10	5	1	1,5	0,5	453
BFR31						1/5	2,5	1,5			453
BFR101A*	30	30	10	200	5	0,2/1,5	1,0	1,2	–	–	517
BFR101B*	30	30	10	200	5	1/5	2,5	2,5	–	–	517
BFT46	25	25	10	250	0,2	0,2/1,5	1,0	1,0	1,5	0,5	545
BSD20*	10	–	50	230	1,0	–	2,0	–	0,6	–	577
BSD22*	20	–	50	230	1,0	–	2,0	–	0,6	–	577
BSR56	40	40	–	250	1	50/–	10	–	5	–	623
BSR57						20/100	6				623
BSR58						8/80	4				623
BSS83*	10	–	50	230	10	–	2,0	–	0,6	–	637
BST80**	80	20	500	1000	100	–/0,01	–	300	8	–	657
BST82	80	20	175	300	100	–/0,001	3,5	150	3	–	661
BST84**	200	20	250	1000	100	–/0,01	–	250	5	–	665
BST86**	180	20	300	1000	100	–/0,01	–	250	6	–	669
BST120**	60	20	300	1000	100	–/0,01	–	200	8	–	673
BST122**	50	20	250	1000	100	–/0,01	–	125	8	–	677
PMBF4391	40	40	–	250	1	50/150	10	–	3,5	–	735
PMBF4392	40	40	–	250	1	25/75	5	–	3,5	–	735
PMBF4393	40	40	–	250	1	5/30	3	–	3,5	–	735

* Types in SOT-143 package are denoted by an asterisk (*).
** Types in SOT-89 package are denoted by two asterisks (**).

TRIGGER DEVICES

P-N-P-N	case	V_{GA} max. V	I_A max. mA	I_P µA	I_V µA	page
BRY61	SOT-23	70	175	5/1	30/50	565
BRY62	SOT-143	70	175	–	–	571

DIODES in SOT-23 unless indicated

type	description	RATINGS V_R V	I_F mA	t_{rr} max. ns	V_F max. (mV) at I_F = mA 10/100	150	C_d max.	page
BA682**	band switch	35	100	–	–/1000	–	1,5	63
BA683**	band switch	35	100	–	–/1000	–	1,5	63
BAS16	high-speed switch	75	250	6	855/–	1250	2	65
BAS17	low-voltage stabilizer	–	250		830/960	–	140	69
BAS19	high-speed switch	100	200	50	–/1000	–	5	73
BAS20	high-speed switch	150	200	50	–/1000	–	5	73
BAS21	high-speed switch	200	200	50	–/1000	–	5	73
BAS28*	fast switch double diode	75	250	6	855/–	1250	2	81
BAS29	switch	90	250	50	750/900	–	35	85
BAS31	two diodes in series	90	250	50	750/900	–	35	85
BAS32**	high-speed switch	75	200	4	–/1000	–	2	87
BAS35	common anode double diode	90	250	50	750/900	–	35	85
BAS56*	ultra-high-speed switch double diode	60	200	6	750/–	–	2,5	95
BAT17	Schottky barrier	4	30	–	600/–	–	1	99
BAT18	band switch	35	100	–	/1200	–	1	103
BAT54	Schottky barrier	30	200	5	400/1000	–	10	107
BAT74*	Schottky barrier; double diode	30	200	5	400/1000	–	10	111
BAV23*	two diodes	200	200	50	–/1000	–	2,5	115
BAV70	common cathode double diode	70	250	6	855/–	1250	1,5	117
BAV99	two diodes in series	70	250	6	855/–	1250	1,5	121
BAV100**	general purpose	50	250	50	–/1000	–	5	125
BAV101**	general purpose	100	250	50	–/1000	–	5	125
BAV102**	general purpose	150	250	50	–/1000	–	5	125
BAV103**	general purpose	200	250	50	–/1000	–	5	125
BAW56	common anode double diode	70	250	6	855/–	1250	2	133

* SOT-143.
** SOD-80.

VARIABLE CAPACITANCE DIODES SOT-23 and SOD-80◄

type	RATINGS		CHARACTERISTICS				page
	V_R	I_F	C_d at V_R		C_d ratio at V_R = 3/25 V at f = 1 MHz	r_D	
	V	mA	pF	V		Ω	
BB215◄	30	20	1,8 – 2,2	28	typ. 8,3	typ. 0,63	137
BB219◄	32	20	2,6 – 3,2	28	12 to 15	typ. 0,7	139
BBY31	28	20	1,8 – 2,8	25	typ. 5	< 1,2	141
BBY40	28	20	4,3 – 6	25	5 to 5,6	< 0,6	145

VOLTAGE REGULATOR DIODES

type	case	range (V)	voltage tolerance %	P_{tot} mW	I_{ZRM} mA	I_{FRM} mA	max. V_F at I_F V	mA	page
BZD27	SOD-87	3,9 to 270	5	2300	–	–	–	–	697
BZV49	SOT-89	2,4 to 75	5	1000	–**	250	1	50	701
BZV55	SOD-80	2,4 to 75	5	500	–	250	0,9	10	711
BZX84	SOT-23	2,4 to 75	5*	350	250	250	0,9	10	725

RECTIFIER DIODES

type	case	$I_{F(AV)}$ A	V_{RRM} V	V_R V	I_{FRM} A	I_{FSM} A	t_{rr} ns	V_F at V	I_F A	page
BYD17D	SOD-87	1,5	200	200	5,5	20	–	1,05	1	693
BYD17G	SOD-87	1,5	400	400	5,5	20	–	1,05	1	693
BYD17J	SOD-87	1,5	600	600	5,5	20	–	1,05	1	693
BYD17K	SOD-87	1,5	800	800	5,5	20	–	1,05	1	693
BYD17M	SOD-87	1,5	1000	1000	5,5	20	–	1,05	1	693
BYD37D	SOD-87	1,5	200	200	12	20	250	1,3	1	697
BYD37G	SOD-87	1,5	400	400	12	20	250	1,3	1	697
BYD37J	SOD-87	1,5	600	600	12	20	250	1,3	1	697
BYD37K	SOD-87	1,5	800	800	12	20	300	1,3	1	697
BYD37M	SOD-87	1,5	1000	1000	12	20	300	1,3	1	697

* Types with 2% tolerance available on request.

** I_{ZRM} limited by P_{ZRMmax}.

In this alpha-numeric list we present all surface mounted devices mentioned in this handbook.

type number	SOT-23	SOT-89	SOT-143	SOD-80	marking type	reverse type	device type	nearest conventional type(s)	complement	page
BA682	–	–	–	●	red band		diode	BA482		63
BA683	–	–	–	●	red and orange		diode	BA483		63
BAS16	●	–	–	–	A6		diode	BAW62, 1N4148		65
BAS17	●	–	–	–	A91		diode	BA314		69
BAS19	●	–	–	–	A8		diode	BAV19		73
BAS20	●	–	–	–	A81		diode	BAV20		73
BAS21	●	–	–	–	A82		diode	BAV21		73
BAS28	–	–	●	–	A61		2 diodes	1N4148		81
BAS29	●	–	–	–	L20		diode	BAX12		85
BAS31	●	–	–	–	L21		2 diodes	BAX12		85
BAS32	–	–	–	●	black band		diode	1N4148		87
BAS35	●	–	–	–	L22		2 diodes	BAX12		85
BAS56	–	–	●	–	L51		2 diodes	BAV10		95
BAT17	●	–	–	–	A3		diode	BA480		99
BAT18	●	–	–	–	A2		diode	BA482		103
BAT54	●	–	–	–	L4		diode	BAT85		107
BAT74	–	–	●	–	L41		2 diodes	BAT85		111
BAV23	–	–	●	–	L30		2 diodes	BAV21		115
BAV70	●	–	–	–	A4		2 diodes	BAW62, 1N4148 (double)		117
BAV99	●	–	–	–	A7		2 diodes	BAW62, 1N4148 (double)		121
BAV100	–	–	–	●	green and black		diode	BAV10		125
BAV101	–	–	–	●	green and brown		diode	BAV19		125
BAV102	–	–	–	●	green and red		diode	BAV20		125
BAV103	–	–	–	●	green and orange		diode	BAV21		125
BAW56	●	–	–	–	A1		diode	BAW62, 1N4148 (double)		133
BB215	–	–	–	●	white and green		diode	BB405B		137
BB219	–	–	–	●	white		diode	BB909		139
BBY31	●	–	–	–	S1		diode	BB405		141
BBY40	●	–	–	–	S2		diode	BB809		145
BC807-16	●	–	–	–	5A	5AR	PNP	BC327-16	BC817-16	149
-25	●	–	–	–	5B	5BR	PNP	-25	-25	149
-40	●	–	–	–	5C	5CR	PNP	-40	-40	149
BC808-16	●	–	–	–	5E	5ER	PNP	BC328-16	BC818-16	149
-25	●	–	–	–	5F	5FR	PNP	-25	-25	149

type number	SOT-23	SOT-89	SOT-143	SOD-80	marking type	reverse type	device type	nearest conventional type(s)	complement	page
BC808-40	●	–	–	–	5G	5GR	PNP	BC328-40	BC818-40	149
BC817-16	●	–	–	–	6A	6AR	NPN	BC337-16	BC807-16	155
-25	●	–	–	–	6B	6BR	NPN	-25	-25	155
-40	●	–	–	–	6C	6CR	NPN	-40	-40	155
BC818-16	●	–	–	–	6E	6ER	NPN	BC328-16	BC808-16	155
BC818-25	●	–	–	–	6F	6FR	NPN	BC328-25	BC808-25	155
-40	●	–	–	–	6G	6GR	NPN	-40	-40	155
BC846A	●	–	–	–	1A	1AR	NPN	BC546A	BC856A	161
BC846B	●	–	–	–	1B	1BR	NPN	BC546B	BC856B	161
BC847A	●	–	–	–	1E	1ER	NPN	BC547A, BC107A	BC857A	161
BC847B	●	–	–	–	1F	1FR	NPN	BC547B, BC107B	BC857B	161
BC847C	●	–	–	–	1G	1GR	NPN	BC547C	BC857C	161
BC848A	●	–	–	–	1J	1JR	NPN	BC548A, BC108A	BC858A	161
BC848B	●	–	–	–	1K	1KR	NPN	BC548B, BC108B	BC858B	161
BC848C	●	–	–	–	1L	1LR	NPN	BC548C, BC108C	BC858C	161
BC849B	●	–	–	–	2B	2BR	NPN	BC549B, BC109B	BC859B	171
BC849C	●	–	–	–	2C	2CR	NPN	BC549C, BC109C	BC859C	171
BC850B	●	–	–	–	2F	2FR	NPN	BC550B, BCY59	BC860B	171
BC850C	●	–	–	–	2G	2GR	NPN	BC550C, BCY59	BC860C	171
BC856A	●	–	–	–	3A	3AR	PNP	BC556A	BC846A	183
BC856B	●	–	–	–	3B	3BR	PNP	BC556B	BC846B	183
BC857A	●	–	–	–	3E	3ER	PNP	BC557A, BC177A	BC847A	183
BC857B	●	–	–	–	3F	3FR	PNP	BC557B, BC177B	BC847B	183
BC857C	●	–	–	–	3G	3GR	PNP	BC557C	BC847C	183
BC858A	●	–	–	–	3J	3JR	PNP	BC558A, BC178A	BC848A	183
BC858B	●	–	–	–	3K	3KR	PNP	BC558B, BC178B	BC848B	183
BC858C	●	–	–	–	3L	3LR	PNP	BC558C	BC848C	183
BC859A	●	–	–	–	4A	4AR	PNP	BC559A, BC179A, BCY78		191
BC859B	●	–	–	–	4B	4BR	PNP	BC559B, BCY79	BC849B	191
BC859C	●	–	–	–	4C	4CR	PNP	BC559C, BCY79	BC849C	191
BC860A	●	–	–	–	4E	4ER	PNP	BC560A, BCY79		191
BC860B	●	–	–	–	4F	4FR	PNP	BC560B, BCY79	BC850B	191
BC860C	●	–	–	–	4G	4GR	PNP	BC560C, BCY79	BC850C	191
BC868	–	●	–	–	CAC		NPN	BC368, BD329	BC869	201
BC869	–	●	–	–	CEC		PNP	BC369, BD330	BC868	207
BCF29	●	–	–	–	C7	C77	PNP	BC559A, BCY78, BC179		213
BCF30	●	–	–	–	C8	C9	PNP	BC559B, BCY78	BCF32	213
BCF32	●	–	–	–	D7	D77	NPN	BC549B, BCY58, BC109	BCF30	221
BCF33	●	–	–	–	D8	D81	NPN	BC549C, BCY58		221
BCF70	●	–	–	–	H7	H71	PNP	BC560B, BCY79		229

type number	SOT-23	SOT-89	SOT-143	SOD-80	marking type	reverse type	device type	nearest conventional type(s)	complement	page
BCF81	●	–	–	–	K9	K91	NPN	BC550C		237
BCV26	●	–	–	–	FD		PNP	BC516	BCV27	241
BCV27	●	–	–	–	FF		NPN	BC517	BCV26	243
BCV61	–	●	–	–	D91		NPN	BC547	BCV62	245
BCV62	–	●	–	–	C91		PNP	BC557	BCV61	249
BCV63	–	–	●	–			NPN		BCV64	253
BCV64	–	–	●	–			PNP		BCV63	257
BCV65	–	–	●	–			PNP/NPN			261
BCV71	●	–	–	–	K7	K71	NPN	BC546A	BCW89	265
BCV72	●	–	–	–	K8	K81	NPN	BC546B		265
BCW29	●	–	–	–	C1	C4	PNP	BC178A, BC558A	BCW31	269
BCW30	●	–	–	–	C2	C5	PNP	BC178B, BC558B	BCW32	269
BCW31	●	–	–	–	D1	D4	NPN	BC108A, BC548A	BCW29	277
BCW32	●	–	–	–	D2	D5	NPN	BC108B, BC548B	BCW30	277
BCW33	●	–	–	–	D3	D6	NPN	BC108C, BC548C		277
BCW60A	●	–	–	–	AA		NPN	BC548A	BCW61A	285
BCW60B	●	–	–	–	AB		NPN	BC548B	BCW61B	285
BCW60C	●	–	–	–	AC		NPN	BC548B	BCW61C	285
BCW60D	●	–	–	–	AD		NPN	BC548C	BCW61D	285
BCW61A	●	–	–	–	BA		PNP	BC558A	BCW60A	289
BCW61B	●	–	–	–	BB		PNP	BC558B	BCW60B	289
BCW61C	●	–	–	–	BC		PNP	BC558B	BCW60C	289
BCW61D	●	–	–	–	BD		PNP	BC558C	BCW60D	289
BCW69	●	–	–	–	H1	H4	PNP	BC557A	BCW71	293
BCW70	●	–	–	–	H2	H5	PNP	BC557B	BCW72	293
BCW71	●	–	–	–	K1	K4	NPN	BC547A	BCW69	301
BCW72	●	–	–	–	K2	K5	NPN	BC547B	BCW70	301
BCW81	●	–	–	–	K3	K31	NPN	BC547C		309
BCW89	●	–	–	–	H3	H31	PNP	BC556A	BCV71	313
BCX17	●	–	–	–	T1	T4	PNP	BC327	BCX19	317
BCX18	●	–	–	–	T2	T5	PNP	BC328	BCX20	317
BCX19	●	–	–	–	U1	U4	NPN	BC337	BCX17	323
BCX20	●	–	–	–	U2	U5	NPN	BC338	BCX18	323
BCX51	–	●	–	–	AA		PNP	BC636, BD136	BCX54	329
BCX52	–	●	–	–	AE		PNP	BC638, BD138	BCX55	329
BCX53	–	●	–	–	AH		PNP	BC640, BD140	BCX56	329
BCX54	–	●	–	–	BA		NPN	BC635, BD135	BCX51	333
BCX55	–	●	–	–	BE		NPN	BC637, BD137	BCX52	333
BCX56	–	●	–	–	BH		NPN	BC639, BD139	BCX53	333
BCX70G	●	–	–	–	AG		NPN	BC107A, BC547A	BCX71G	337

type number	SOT-23	SOT-89	SOT-143	SOD-80	marking type	reverse type	device type	nearest conventional type(s)	complement	page
BCX70H	●	–	–	–	AH		NPN	BC107B, BC547B	BCX71H	337
BCX70J	●	–	–	–	AJ		NPN	BC107B, BC547B	BCX71J	337
BCX70K	●	–	–	–	AK		NPN	BC107C, BC547C	BCX71K	337
BCX71G	●	–	–	–	BG		PNP	BC177A, BC557A	BCX70G	341
BCX71H	●	–	–	–	BH		PNP	BC177B, BC557B	BCX70H	341
BCX71J	●	–	–	–	BJ		PNP	BC177B, BC557B	BCX70J	341
BCX71K	●	–	–	–	BK		PNP	BC557C	BCX70K	341
BF510	●	–	–	–	S6		FET	BF410A		345
BF511	●	–	–	–	S7		FET	BF410B		345
BF512	●	–	–	–	S8		FET	BF410C		345
BF513	●	–	–	–	S9		FET	BF410D		345
BF536	●	–	–	–	G3		PNP	BF936		351
BF550	●	–	–	–	G2	G5	PNP	BF450		355
BF569	●	–	–	–	G6		PNP	BF970		359
BF570	●	–	–	–	B26		NPN	BF370		363
BF579	●	–	–	–	G7		PNP	BF979		367
BF620	–	●	–	–	DC		NPN	BF420, BF471, BF871	BF621	371
BF621	–	●	–	–	DF		PNP	BF421, BF472, BF872	BF620	375
BF622	–	●	–	–	DA		NPN	BF422, BF469, BF869	BF623	371
BF623	–	●	–	–	DB		PNP	BF423, BF470, BF870	BF622	375
BF660	●	–	–	–	G8	G81	PNP	BF606A		379
BF767	●	–	–	–	G9		PNP	BF967		383
BF820	●	–	–	–	1V		NPN	BF420	BF821	387
BF821	●	–	–	–	1W		PNP	BF421	BF820	393
BF822	●	–	–	–	1X		NPN	BF422	BF823	387
BF823	●	–	–	–	1Y		PNP	BF423	BF822	393
BF824	●	–	–	–	F8		PNP	BF324		399
BF840	●	–	–	–	F3		NPN	BF240		405
BF841	●	–	–	–	F31		NPN	BF241		405
BF989	–	–	●	–	M89		FET	BF960		407
BF990	–	–	●	–	M90		FET	BF980		409
BF991	–	–	●	–	M91		FET	BF981		413
BF992	–	–	●	–	M92		FET	BF982		415
BF994	–	–	●	–	M94		FET	BF964		417
BF994S	–	–	●	–	M93		FET	BF964S		421
BF996	–	–	●	–	M96		FET	BF966		423
BF996S	–	–	●	–	M95		FET	BF966S		427
BF997	–	–	●	–	M83		FET			429
BFG67	–	–	●	–	V3		NPN	BFG65		433
BFQ17	–	●	–	–	FA		NPN	BFW16A		437

type number	SOT-23	SOT-89	SOT-143	SOD-80	marking type	reverse type	device type	nearest conventional type(s)	complement	page
BFQ18A	–	●	–	–	FF		NPN	BFQ34		441
BFQ19	–	●	–	–	FB		NPN	BFR96		445
BFQ67	●	–	–	–	V2		NPN	BFQ65		449
BFR30	●	–	–	–	M1		FET	BFW11, BF245		453
BFR31	●	–	–	–	M2		FET	BFW12, BF245		453
BFR53	●	–	–	–	N1	N4	NPN	BFW30, BFW93		463
BFR92	●	–	–	–	P1	P4	NPN	BFR90	BFT92	473
BFR92A	●	–	–	–	P2	P5	NPN	BFR90		483
BFR93	●	–	–	–	R1	R4	NPN	BFR91	BFT93	495
BFR93A	●	–	–	–	R2	R5	NPN	BFR91		505
BFR101A	–	–	●	–	M97		FET	–		517
BFR101B	–	–	●	–	M98		FET	–		517
BFS17	●	–	–	–	E1	E4	NPN	BFY90, BFW92		519
BFS18	●	–	–	–	F1	F4	NPN	BF185, BF495		525
BFS19	●	–	–	–	F2	F5	NPN	BF184, BF494		525
BFS20	●	–	–	–	G1	G4	NPN	BF199		531
BFT25	●	–	–	–	V1	V4	NPN	BFT24		537
BFT46	●	–	–	–	M3		FET	BFW13, BF245		545
BFT92	●	–	–	–	W1	W4	PNP	BFQ51; 52	BFR92	553
BFT93	●	–	–	–	X1	X4	PNP	BFQ23; 24	BFR93	559
BRY61	●	–	–	–	A5		PNPN	BRY56, BRY39		565
BRY62	●	–	–	–	A51		PNPN	BRY39		571
BSD20	–	●	–	–	M31		FET	–		577
BSD22	–	●	–	–	M32		FET	–		577
BSR12	●	–	–	–	B5	B8	PNP	2N2894A	BSV52	581
BSR13	●	–	–	–	U7	U71	NPN	2N2222, PH2222	BSR15	587
BSR14	●	–	–	–	U8	U81	NPN	2N2222A, PH2222A	BSR16	587
BSR15	●	–	–	–	T7	T71	PNP	2N2907, PH2907	BSR13	593
BSR16	●	–	–	–	T8	T81	PNP	2N2907A, PH2907A	BSR14	593
BSR17	●	–	–	–	U9	U91	NPN	2N3903	BSR18	599
BSR17A	●	–	–	–	U92	U93	NPN	2N3904	BSR18A	599
BSR18	●	–	–	–	T9	T91	PNP	2N3905	BSR17	603
BSR18A	●	–	–	–	T92	T93	PNP	2N3906	BSR17A	603
BSR19	●	–	–	–	U35		NPN	2N5550	BSR20	607
BSR19A	●	–	–	–	U36		NPN	2N5551	BSR20A	607
BSR20	●	–	–	–	T35		PNP	2N5400	BSR19	611
BSR20A	●	–	–	–	T36		PNP	2N5401	BSR19A	611
BSR30	–	●	–	–	BR1		PNP	2N4030	BSR40	615
BSR31	–	●	–	–	BR2		PNP	2N4032	BSR41	615
BSR32	–	●	–	–	BR3		PNP	2N4031	BSR42	615

type number	SOT-23	SOT-89	SOT-143	SOD-80	marking type	reverse type	device type	nearest conventional type(s)	complement	page
BSR33	–	●	–	–	BR4		PNP	2N4033	BSR43	615
BSR40	–	●	–	–	AR1		NPN	BSX46-6	BSR30	619
BSR41	–	●	–	–	AR2		NPN	BSX46-16	BSR31	619
BSR42	–	●	–	–	AR3		NPN	2N3020	BSR32	619
BSR43	–	●	–	–	AR4		NPN	2N3019	BSR33	619
BSR56	●	–	–	–	M4		FET	2N4856		623
BSR57	●	–	–	–	M5		FET	2N4857		623
BSR58	●	–	–	–	M6		FET	2N4858		623
BSS63	●	–	–	–	T3	T6	PNP	BSS68	BSS64	627
BSS64	●	–	–	–	U3	U6	NPN	BSS38	BSS63	633
BSS83	–	–	●	–	M74		FET			637
BST15	–	●	–	–	BT1		PNP	2N5415	BST40	641
BST16	–	●	–	–	BT2		PNP	2N5416	BST39	641
BST39	–	●	–	–	AT1		NPN	2N3439	BST16	645
BST40	–	●	–	–	AT2		NPN	2N3440	BST15	645
BST50	–	●	–	–	AS1		NPN	BSR50, BSS50, BDX42		649
BST51	–	●	–	–	AS2		NPN	BSR51, BSS51, BDX43		649
BST52	–	●	–	–	AS3		NPN	BSR52, BSS52, BDX44		649
BST60	–	●	–	–	BS1		PNP	BSR60, BSS60, BDX45		653
BST61	–	●	–	–	BS2		PNP	BSR61, BSS61, BDX46		653
BST62	–	●	–	–	BS3		PNP	BSR62, BSS62, BDX47		653
BST80	–	●	–	–	KM		FET	BST70A		657
BST82	●	–	–	–	O2		FET	BST72A		661
BST84	–	●	–	–	KN		FET	BST74A		665
BST86	–	●	–	–	KO		FET	BST76A		669
BST120	–	●	–	–	LM		FET			673
BST122	–	●	–	–	LN		FET			677
BSV52	●	–	–	–	B2	B3	NPN	PH2369, BSX20	BSR12	681
BYD17	SOD-87						diode			689
BYD37	SOD-87						diode			693
BZD27	SOD-87						diode			697
BZV49	–	●	–	–	*		diode	BZV85		701
BZV55	–	–	–	●			diode	BZX79, BZX55		711
BZX84	●	–	–	–	*		diode	BZX79, BZX55		725
PMBF4391	●	–	–	–	M62		FET	2N4301		735
PMBF4392	●	–	–	–	M63		FET	2N4392		735
PMBF4393	●	–	–	–	M64		FET	2N4393		735
PMBT2222	●	–	–	–	P1B		NPN	2N2222	PMBT2907	739
PMBT2222A	●	–	–	–	P1P		NPN	2N2222A	PMBT2907A	739
PMBT2907	●	–	–	–	P2B		PNP	2N2907	PMBT2222	743
PMBT2907A	●	–	–	–	P2F		PNP	2N2907A	PMBT2222A	743

* For marking of these types see page 20.

type number	SOT-23	SOT-89	SOT-143	SOT-80	marking type reverse type	device type	nearest conventional type(s)	complement	page
PMBT3903	●	–	–	–	P1Y	NPN	2N3903	PMBT3905	749
PMBT3904	●	–	–	–	P1A	NPN	2N3904	PMBT3906	749
PMBT3906	●	–	–	–	P2A	PNP	2N3906	PMBT3904	753
PMBT6428	●	–	–	–	P1K	NPN	2N6428		757
PMBT6429	●	–	–	–	P1L	NPN	2N6429		757
PMBTA05	●	–	–	–	P1H	NPN	MPSA05	PMBTA55	761
PMBTA06	●	–	–	–	P1G	NPN	MPSA06	PMBTA56	761
PMBTA13	●	–	–	–	P1M	NPN	MPSA13	PMBTA63	763
PMBTA14	●	–	–	–	P1N	NPN	MPSA14	PMBTA64	763
PMBTA42	●	–	–	–	P1D	NPN	MPSA42	PMBTA94	765
PMBTA43	●	–	–	–	P1E	NPN	MPSA43	PMBTA93	765
PMBTA55	●	–	–	–	P2G	NPN	MPSA55	PMBTA05	769
PMBTA56	●	–	–	–	P2H	NPN	MPSA56	PMBTA06	769
PMBTA63	●	–	–	–	P2U	PNP	MPSA63	PMBTA13	771
PMBTA64	●	–	–	–	P2V	PNP	MPSA63	PMBTA14	771
PMBTA92	●	–	–	–	P2D	PNP	MPSA92	PMBTA42	773
PMBTA93	●	–	–	–	P2E	PNP	MPSA93	PMBTA43	773
PMLL5225B to PMLL5267B	–	–	–	●		diode	1N5225B to 1N5267B		775
PXT3904	–	●	–	–	P1A	NPN	2N3904	PXT3906	779
PXT3906	–	●	–	–	P2A	PNP	2N3906	PXT3904	783

type	BZV49- SOT-89 page 701	BZX84- SOT-23 page 725
device type	diode	diode
nearest conventional type	BZV85 series	BZX79 series
type number suffix	mark	mark
C2V4	2Y4	Z11
C2V7	2Y7	Z12
C3V0	3Y0	Z13
C3V3	3Y3	Z14
C3V6	3Y6	Z15
C3V9	3Y9	Z16
C4V3	4Y3	Z17
C4V7	4Y7	Z1
C5V1	5Y1	Z2
C5V6	5Y6	Z3
C6V2	6Y2	Z4
C6V8	6Y8	Z5
C7V5	7Y5	Z6
C8V2	8Y2	Z7
C9V1	9Y1	Z8
C10	10Y	Z9
C11	11Y	Y1
C12	12Y	Y2
C13	13Y	Y3
C15	15Y	Y4
C16	16Y	Y5
C18	18Y	Y6
C20	20Y	Y7
C22	22Y	Y8
C24	24Y	Y9
C27	27Y	Y10
C30	30Y	Y11
C33	33Y	Y12
C36	36Y	Y13
C39	39Y	Y14
C43	43Y	Y15
C47	47Y	Y16
C51	51Y	Y17
C56	56Y	Y18
C62	62Y	Y19
C68	68Y	Y20
C75	75Y	Y21

CONVERSION LIST

(conventional type number to SMD type number)

conventional type	microminiature type
BA314	BAS17
BA480	BAT17
BA482	BA682
BA483	BA683
BAT85	BAT54
	BAT74
BAV10	BAS56
BAV18	BAV100
BAV19	BAS19
	BAV101
BAV20	BAS20
	BAV102
BAW62	BAS16
	BAS28
	BAS32
	BAV70
	BAV99
	BAW56
BAX12	BAS29
	BAS31
	BAS35
BB405	BBY31
BB809	BBY40
BC107	BC847
	BCW71/72
BC107A	BC847A
	BCW71
BC107B	BC847B
	BCW72
BC108	BC848
	BCW31-33
BC108A	BC848A
	BCW31
BC108B	BC848B
	BCW32
BC109	BC849
	BCF32/33
BC109B	BC849B
	BCF32
BC109C	BC849C
	BCF33
BC146/01	BC849B
	BCF32
BC146/02	BC849B/C
	BCF32/33
BC146/03	BC849C
	BCF33

conventional type	microminiature type
BC177	BC857
	BCW69/70
BC177A	BC857A
	BCW69
BC177B	BC857B
	BCW70
BC178	BC858
	BCW29/30
BC178A	BC858A
	BCW29
BC178B	BC858B
	BCW30
BC179	BC859
	BCF29/30
BC179A	BC859A
	BCF29
BC179B	BC859B
	BCF30
BC200/01	BC859B
	BCF29
BC200/02	BC859B/C
	BCF29/30
BC200/03	BC859C
	BCF30
BC327	BC807
	BCX17
BC327-16	BC807-16
BC327-25	BC807-25
BC327-40	BC807-40
BC327A	
BC328	BC808
BC328-16	BC808-16
BC328-25	BC808-25
BC328-40	BC808-40
BC337	BC817
	BCX19
BC337-16	BC817-16
BC337-25	BC817-25
BC337-40	BC817-40
BC338	BC818
	BCX20
BC338-16	BC818-16
BC338-25	BC818-25
BC338-40	BC818-40
BC368	BC868
BC369	BC869
BC516	BCV26

conventional type	microminiature type
BC517	BCV27
BC546	BC846
	BCV71/72
BC546A	BC846A
	BCV71
BC546B	BC846B
	BCV72
BC547	BC847
	BCW71/71/81
BC547A	BC847A
	BCW71
BC547B	BC847B
	BCW72
BC547C	BC847C
	BCW81
BC548	BC848
	BCW31-33
BC548A	BC848A
	BCW31
BC548B	BC848B
	BCW32
BC548C	BC848C
	BCW33
BC549	BC849
	BCF32/33
BC549B	BC849B
	BCF32
BC549C	BC849C
	BCF33
BC550	BC850
	BCF81
BC550B	BC850B
BC550C	BC850C
BC556	BC856
	BCW89
BC556A	BC856A
	BCW89
BC556B	BC856B
BC557	BC857
	BCW69/70
BC557A	BC857A
	BCW69
BC557B	BC857B
	BCW70
BC557C	BC857C
BC558	BC858
	BCW29/30

conventional type	microminiature type
BC558A	BC858A
	BCW29
BC558B	BC858B
	BCW30
BC558C	BC858C
BC559	BC859
	BCF29/30
BC559A	BC859A
	BCF29
BC559B	BC859B
	BCF30
BC559C	BC859C
BC560	BC860
	BCF70
BC560A	BC860A
BC560B	BC860B
	BCF70
BC560C	BC860C
BC635	BCX54
BC635-6	BCX54-6
BC635-10	BCX54-10
BC635-16	BCX54-16
BC636	BCX51
BC636-6	BCX51-6
BC636-10	BCX51-10
BC636-16	BCX51-16
BC637	BCX55
BC637-6	BCX55-6
BC637-10	BCX55-10
BC637-16	BCX55-16
BC638	BCX52
BC638-6	BCX52-6
BC638-10	BCX52-10
BC638-16	BCX52-16
BC639	BCX56
BC639-6	BCX56-6
BC639-10	BCX56-10
BC639-16	BCX56-16
BC640	BCX53
BC640-6	BCX53-6
BC640-10	BCX53-10
BC640-16	BCX53-16
BCY56	BC850B
	BCF70
BCY57	BC849
	BCF32/33
BCY58	BC849
	BCW60 fam.
BCY58-VII	BCW60A
BCY58-VIII	BC849B
	BCW60B

conventional type	microminiature type
BCY58-IX	BC849B
	BCW60C
BCY58-X	BC849C
	BCW60D
BCY59	BC850
	BCX70 fam.
BCY59-VII	BCX70G
BCY59-VIII	BC850B
	BCX70H
BCY59-IX	BC850B
	BCX70J
BCY59-X	BC850C
	BCX70K
BCY70	BC860
	BCF70
BCY71	BC860
	BCF70
BCY72	BC859
	BCF29/30
BCY78	BC859
	BCW61 fam.
BCY78-VII	BC859A
	BCW61A
BCY78-VIII	BC859A/B
	BCW61B
BCY78-IX	BC859B
	BCW61C
BCY78-X	BV859C
	BCW61D
BCY79	BC860
	BCX71 fam.
BCY79-VII	BC860A
	BCX71G
BCY79-VIII	BC860A/B
	BCX71H
BCY79-IX	BC860B
	BCX71J
BD135	BCX54
BD135-6	BCX54-6
BD135-10	BCX54-10
BD135-16	BCX54-16
BD136	BCX51
BD136-6	BCX51-6
BD136-10	BCX51-10
BD136-16	BCX51-16
BD137	BCX55
BD137-6	BCX55-6
BD137-10	BCX55-10
BD137-16	BCX55-16
BD138	BCX52
BD138-6	BCX52-6
BD138-10	BCX52-10

conventional type	microminiature type
BD138-16	BCX52-16
BD139	BCX56
BD139-6	BCX56-6
BD139-10	BCX56-10
BD139-16	BCX56-16
BD140	BCX53
BD140-6	BCX53-6
BD140-10	BCX53-10
BD140-16	BCX53-16
BDX42	BST50
BDX43	BST51
BDX44	BST52
BDX45	BST60
BDX46	BST61
BDX47	BST61
BF198	
BF199	BFS20
BF240	BF840
BF241	BF841
BF324	BF824
BF370	BSV52
	BF570
BF410A	BF510
BF410B	BF511
BF410C	BF512
BF410D	BF513
BF419	BST40
BF420	BF620
	BF820
BF421	BF621
	BF821
BF422	BF622
	BF822
BF423	BF623
	BF823
BF450	BF550
BF451	
BF457	BST40
BF458	BST40
BF459	BST39
BF469	BF622
BF470	BF623
BF471	BF620
BF472	BF621
BF494	BFS19
BF494B	BFS19
BF495	BFS18
BF495C	BFS18
BF495D	BFS18
BF606A	BF660
BF819	BST40
BF857	BST40

conventional type	microminiature type	conventional type	microminiature type	conventional type	microminiature type
BF858	BST40	BFY52	BSR40	MPSA14	PMBTA14
BF859	BST39	BFY55	BSR40	MPSA42	PMBTA42
BF869	BF622	BFY90	BFS17	MPSA43	PMBTA43
BF870	BF623	BR101	BRY62	MPSA55	PMBTA55
BF871	BF620	BRY39	BRY62	MPSA56	PMBTA56
BF872	BF621	BRY56	BRY61	MPSA63	PMBTA63
BF926	BF660	BSR50	BST50	MPSA92	PMBTA92
BF936	BF536	BSR51	BST51	MPSA93	PMBTA93
BF939		BSR52	BST52	PH2222	BSR13
BF960	BF989	BSR60	BST60	PH2222A	BSR14
BF964	BF994	BSR61	BST61	PH2369	BSV52
	BF994S	BSR62	BST62	PH2907	BSR15
BF966	BF996	BSS38	BSS64	PH2907A	BSR16
	BF996S	BSS50	BST50	1N4148	BAS16
BF967	BF767	BSS51	BST51		BAV90
BF970	BF569	BSS52	BST52		BAV99
BF979	BF579	BSS60	BST60		BAW56
BF980	BF990	BSS61	BST61	1N5225B	PMLL5225B
BF981	BF991	BSS62	BST62	to	to
BF982	BF992	BSS68	BSS63	1N5267B	PMLL5267B
BFG65	BFG67	BSV15	BSR30/31	2N929	BC850
BFQ23	BFT93	BSV15-6	BSR30	2N930	BNC850
BFQ24	BFT93	BSV15-10	BSR30/31		BCF81
BFQ34	BFQ18A	BSV15-16	BSR31	2N1613	BSR40
BFQ34T	BFQ18A	BSV16	BSR30/31	2N1711	BSR41
BFQ51	BFT92	BSV16-6	BSR30	2N1893	BSR42
BFQ52	BFT92	BSV16-10	BSR30/31	2N2219	BSR13
BFQ65	BFQ67	BSV16-16	BSR31	2N2219A	BSR14
BFR54	BSV52	BSV17	BSR32/33	2N2222	BSR13
BFR90	BFR92A	BSV17-6	BSR32		PMBT2222
BFR91	BFR93A	BSV17-10	BSR32/33	2N2222A	BSR14
BFR96	BFQ19	BSX19	BSV52		PMBT2222A
BFR96S	BFQ19	BSX20	BSV52	2N2297	BSR40
BFT24	BFT25	BSX45	BSR40/41	2N2368	BSV52
BFT44	BST16	BSX45-6	BSR40	2N2369	BSV52
BFT45	BST15/16	BSX45-10	BSR40/41	2N2369A	BSV52
BFW11	BFR30	BSX45-16	BSR41	2N2483	BC850B
BFW12	BFR31	BSX46	BSR40/41	2N2484	BC850B/C
BFW13	BFT46	BSX46-6	BSR40	2N894A	BSR12
BFW16A	BFQ17	BSX46-10	BSR40/41	2N2905	BSR15
BFW30	BFR53	BSX46-16	BSR41	2N2905A	BSR16
BFW92	BFS17	BSX47	BSR42/43	2N2907	BSR15
BFW93	BFR53	BSX47-6	BSR42		PMBT2907
BFX29	BSR16	BSX47-10	BSR42/43	2N2907A	BSR16
BFX30	BSR16	BSY95A	BSV52		PMBT2907A
BFX84	BSR40	BZX55	BZX84	2N3019	BSR43
BFX85	BSR41	BZX79	BZX84	2N3020	BSR42
BFX86	BSR41		BZV55	2N3053	BSR40/41
BFX87	BSR16	BZV85	BZV49	2N3903	BSR17
BFX88	BSR15	MPSA05	PMBTA05		PMBT3903
BFY50	BSR40	MPSA06	PMBTA06	2N3904	BSR17A
BFY51	BSR40	MPSA13	PMBTA13		PMBT3904

conventional type	microminiature type
2N3905	BSR18
2N3906	BSR18A
	PMBT3906
2N4030	BSR30
2N4031	BSR32
2N4032	BSR31
2N4033	BSR33
2N4123	BSR17
2N4124	BSR18
2N4856	BSR56
2N4857	BSR57
2N4858	BSR58
2N5415	BST15
2N5416	BST16
2N6428	PMBT6428
2N6429	PMBT6429

MARKING LIST

Types in SOT-23, SOT-89 and SOT-143 envelopes are marked with a code as listed below. The actual type number and data code are on the packing.

Types in SOT-89 usually have the type number marked in full on the envelope. An exception to this is the BZV-49 series.

The envelope number is mentioned in those cases where the same marking code appears twice.

mark	type no.
AT1	BST39
AT2	BST40
B1	
B2	BSV52
B3	
B4	BSV52R
B5	BSR12
B6	
B7	
B8	BSR12R
B26	BF570
BA	BCW61A (SOT-23)
BA	BCX54 (SOT-89)
BB	BCW61B (SOT-23)
BB	BCX54-6 (SOT-89)
BC	BCW61C (SOT-23)
BC	BCX54-10 (SOT-89)
BD	BCW61D (SOT-23)
BD	BCX54-16 (SOT-89)
BE	BCX55
BF	BCX55-6
BG	BCX71G (SOT-23)
BG	BCX55-10 (SOT-89)
BH	BCX71H (SOT-23)
BH	BCX56 (SOT-89)
BJ	BCX71J (SOT-23)
BJ	BCX56-6 (SOT-89)
BK	BCX71K (SOT-23)
BK	BCX56-10 (SOT-89)
BL	BCX56-16
BM	BCX55-16
BR1	BSR30
BR2	BSR31
BR3	BSR32
BR4	BSR33
BS1	BST60
BS2	BST61
BS3	BST62
A1	BAW56
A2	BAT18
A3	BAT17
A4	BAV70
A5	BRY61
A51	BRY62
A6	BAS16
A61	BAS28
A7	BAV99
A8	BAS19
A81	BAS20
A82	BAS21
A9	
A91	BAS17
AA	BCW60A (SOT-23)
AA	BCX51 (SOT-89)
AB	BCW60B (SOT-23)
AB	BCX51-6 (SOT-89)
AC	BCW60C (SOT-23)
AC	BCX51-10 (SOT-89)
AD	BCW60D (SOT-23)
AD	BCX51-16 (SOT-89)
AE	BCX52
AF	BCX52-6
AG	BCX70G
AH	BCX70H (SOT-23)
AH	BCX53 (SOT-89)
AJ	BCX70J (SOT-23)
AJ	BCX53-6 (SOT-89)
AK	BCX70K (SOT-23)
AK	BCX53-10 (SOT-89)
AL	BCX53-16
AM	BCX52-16
AR1	BSR40
AR2	BSR41
AR3	BSR42
AR4	BSR43
AS1	BST50
AS2	BST51
AS3	BST52

mark	type no.	mark	type no.	mark	type no.	mark	type no.
BT1	BST15	F3	BF840	K4	BCW71R	M9	
BT2	BST16	F31	BF841	K5	BCW72R	M90	BF990
C1	BCW29	F4	BFS18R	K6		M91	BF991
C2	BCW30	F5	BFS19R	K7	BCV71	M92	BF992
C3		F6		K71	BCV71R	M93	BF994S
C4	BCW29R	F7		K8	BCV72	M94	BF994
C5	BCW30R	F8	BF824	K81	BCV72R	M95	BF996S
C6		F9		K9	BCF81	M96	BF996
C7	BCF29	FA	BFQ17	K91	BCF81R	M97	BFR101A
C77	BCF29R	FB	BFQ19	KM	BST80	M98	BFR101B
C8	BCF30	FD	BCV26	KN	BST84	N1	BFR53
C9	BCF30R	FF	BCV27	KO	BST86	N2	
C91	BCV62	(SOT-23)		L2		N3	
CAC	BC868	FF	BFQ18A	L20	BAS29	N4	BFR53R
CEC	BC869	(SOT-89)		L21	BAS31	N5	
D1	BCW31	G1	BFS20	L22	BAS35	N6	
D2	BCW32	G2	BF550	L3		N7	
D3	BCW33	G3	BF536	L30	BAV23	N8	
D4	BCW31R	G4	BFS20R	L4	BAT54	N9	
D5	BCW32R	G5	BF550R	L41	BAT74	P1	BFR92
D6	BCW33R	G6	BF569	L5		P1A	PMBT3904
D7	BCF32	G7	BF579	L51	BAS56	P1B	PMBT2222
D77	BCF32R	G8	BF660	LM	BST120	P1D	PMBTA42
D8	BCF33	G81	BF660R	LN	BST122	P1E	PMBTA43
D81	BCF33R	G9	BF767	M1	BFR30	P1G	PMBTA05
D91	BCV61	H1	BCW69	M2	BFR32	P1H	PMBTA06
DA	BF622	H2	BCW70	M3	BFT46	P1K	PMBT6428
DB	BF623	H3	BCW89	M31	BSD20	P1L	PMBT6429
DC	BF620	H31	BCW89R	M32	BSD22	P1M	PMBTA13
DF	BF621	H4	BCW69R	M4	BSR56	P1N	PMBTA14
E1	BFS17	H5	BCW70R	M5	BSR57	P1P	PMBT2222A
E2		H6		M6	BSR58	P1Y	PMBT3903
E3		H7	BCF70	M61		P2	BFR92A
E4	BFS17R	H71	BCF70R	M62	PBMF4391	P2A	PMBT3906, PXT3906
E5		H8		M63	PBMF4392	P2B	PMBT2907, PXT3904
E6		H9		M64	PBMF4393	P2D	PMBTA92
E7		K1	BCW71	M74	BSS83	P2E	PMBTA93
E8		K2	BCW72	M8		P2F	PMBT2907A
F1	BFS18	K3	BCW81	M83	BF997	P2G	PMBTA55
F2	BFS19	K31	BCW81R	M89	BF989	P2H	PMBTA56

mark	type no.	mark	type no.	mark	type no.	mark	type no.
P2U	PMBTA63	T93	BSR18AR	X9		1E	BC847A
P2V	PMBTA64	U1	BCX19	Y1	BZX84-C11	1ER	BC847AR
P3		U2	BCX20	Y2	-C12	1F	BC847B
P4	BFR92R	U3	BSS64	Y3	-C13	1FR	BC847BR
P5	BFR92AR	U4	BCX19R	Y4	-C15	1G	BC847C
P6		U5	BCX20R	Y5	BZX84-C16	1GR	BC847CR
P7		U6	BSS64R	Y6	-C18	1J	BC848A
P8		U7	BSR13	Y7	-C20	1JR	BC848AR
P9		U8	BSR14	Y8	-C22	1K	BC848B
R1	BFR93	U81	BSR14R	Y9	-C24	1KR	BC848BR
R2	BFR93A	U9	BSR17	Y10	BZX84-C27	1L	BC848C
R3		U91	BSR17R	Y11	-C30	1LR	BC848CR
R4	BFR93R	U92	BSR17A	Y12	-C33	1V	BF820
R5	BFR93AR	U93	BSR17AR	Y13	-C36	1W	BF821
R6		V1		Y14	-C39	1X	BF822
R7		V2	BFQ67	Y15	-C43	1Y	BF823
R8		V3	BFG67	Y16	-C47	2B	BC849B
R9		V4	BFT25R	Y17	-C51	2BR	BC849BR
S1	BBY31	V5		Y18	-C56	2C	BC849C
S2	BBY40	V6		Y19	-C62	2CR	BC849CR
S3		V7		Y20	-C68	2F	BC850B
S4		V8		Y21	-C75	2FR	BC850BR
S5		V9		Z1	-C4V7	2G	BC850C
S6	BF510	W1	BFT92	Z2	-C5V1	2GR	BC850CR
S7	BF511	W2		Z3	-C5V6	2Y4	BZV49-C2V4
S8	BF512	W3		Z4	-C6V2	2Y7	BZV49-C2V7
S9	BF513	W4	BFT92R	Z5	-C6V8	3A	BC856A
T1	BCX17	W5		Z6	-C7V5	3AR	BC856AR
T2	BCX18	W6		Z7	-C8V2	3B	BC856B
T3	BSS63	W7		Z8	-C9V1	3BR	BC856BR
T4	BCX17R	W8		Z9	-C10	3E	BC857A
T5	BCX18R	W9		Z11	-C2V4	3ER	BC857AR
T6	BSS63R	X1	BFT93	Z12	-C2V7	3F	BC857B
T7	BSR15	X2		Z13	-C3V0	3FR	BC857BR
T71	BSR15R	X3		Z14	-C3V3	3J	BC858A
T8	BSR16	X4	BFT93R	Z15	-C3V6	3JR	BC858AR
T81	BSR16R	X5		Z16	-C3V9	3G	BC857C
T9	BSR18	X6		Z17	-C4V3	3GR	BC857CR
T91	BSR18R	X7		1A	BC846A	3K	BC858B
T92	BSR18A	X8		1BR	BC846AR	3KR	BC858BR

mark	type no.	mark	type no.	mark	type no.	mark	type no.
3L	BC858C	6E	BC818-16				
3LR	BC858CR	6ER	BC818-16R				
3Y0	BZV49-C3V0	6F	BC818-25				
3Y3	BZV49-C3V3	6FR	BC818-25R				
3Y6	BZV49-C3V6	6G	BC818-40				
3Y9	BZV49-C3V9	6GR	BC818-40R				
4A	BC859A	6Y2	BZV49-C6V2				
4AR	BC859AR	6Y8	-C6V8				
4B	BC859B	7Y5	-C7V5				
4BR	BC859BR	8Y2	-C8V2				
4C	BC859C	9Y1	-C9V1				
4CR	BC859CR	10Y	-C10				
4E	BC860A	11Y	-C11				
4ER	BC860AR	12Y	-C12				
4F	BC860B	13Y	-C13				
4FR	BC860BR	15Y	-C15				
4G	BC860C	16Y	-C16				
4GR	BC860CR	18Y	-C18				
4Y3	BZV49-C4V3	20Y	-C20				
4Y7	BZV49-C4V7	22Y	-C22				
5A	BC807-16	24Y	-C24				
5AR	BC807-16R	27Y	-C27				
5B	BC807-25	30Y	-C30				
5BR	BC807-25R	33Y	-C33				
5C	BC807-40	36Y	-C36				
5CR	BC807-40R	39Y	BZV49-C39				
5E	BC808-16	43Y	-C43				
5ER	BC808-16R	47Y	-C47				
5F	BC808-25	51Y	-C51				
5FR	BC808-25R	56Y	-C56				
5G	BC808-40	62Y	-C62				
5GR	BC808-40R	68Y	-C68				
5Y1	BZV49-C5V1	75Y	-C75				
5Y6	BZV49-C5V6						
6A	BC917-16						
6AR	BC817-16R						
6B	BC817-25						
6BR	BC817-25R						
6C	BC817-40						
6CR	BC817-40R						

TAPE AND REEL SPECIFICATION

Semiconductors in SOT-23, SOT-143 and SOT-89 encapsulations can be delivered in reel packing for aotomatic placement on hybrid circuits and printed circuit boards. The devices are placed with the mounting side downwards in compartments.

A separate cross-section for SOD-80 encapsulation is given in Fig. 3.

A separate reel packing for SOT-89 encapsulation is given in Fig. 4.

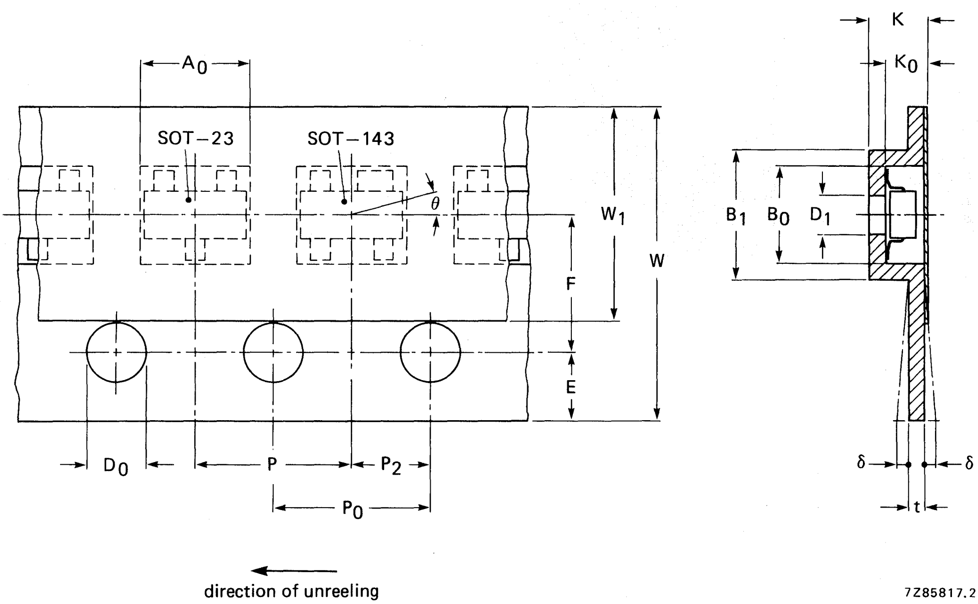


Fig. 1 Configuration of bandolier. Dimensions in mm.

Compartment			tol.
length	A_0 component length		+0,2
width	B_0 component width		+0,2
depth	K_0	0,95	+0,2
width outside	B_1	3,3	max.
pitch	P	4,0	±0,1
deviation	Θ	15°	max.
hole diameter	D_1	1	min.
Sprocket hole			
diameter	D_0	1,5	+0,1
pitch	P_0	4,0	±0,1
distance	E	1,75	±0,1
cumulative (10) pitch error		±0,1	

Centre line dimensions			tol.
length direction	P_2	2,0	±0,05
width direction	F	3,5	±0,05
Fixing tape			
width	W_1	5,5	±0,25
thickness	—	0,1	max.
Carrier tape			
width	W	8,0	±0,2
bending	δ	0,3	max.
thickness	t	0,4	max.
Overall thickness	K	1,5	max.

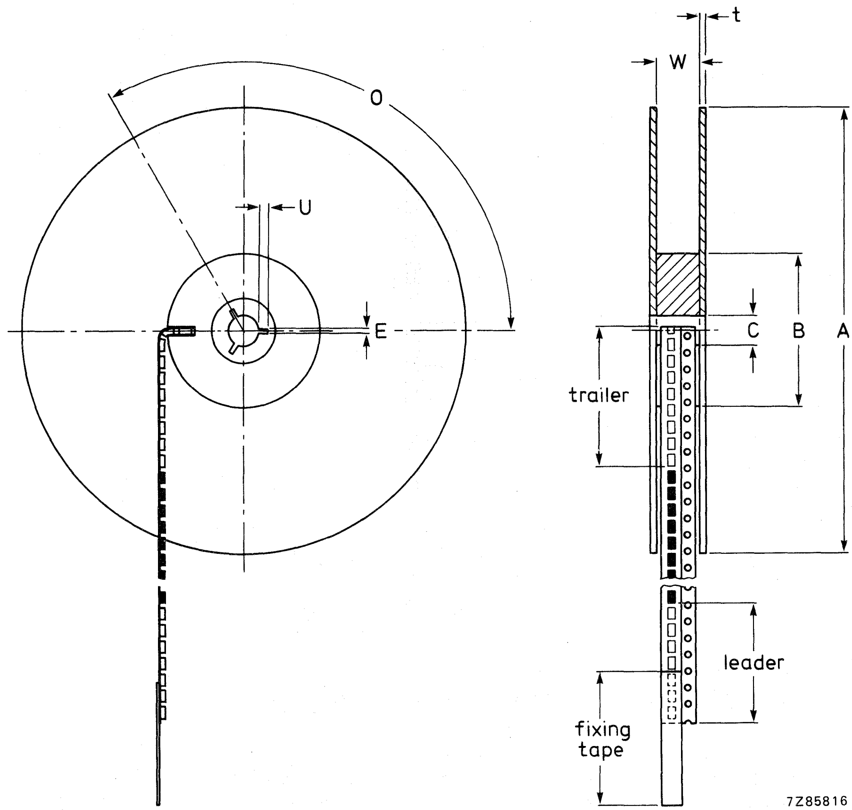


Fig. 2 Configuration of reel and flange (dimensions in mm).

Flange			tol.
diameter	A	180	+0 −2
thickness	t	1,5	+0,5 −0,1
space between flanges	W	9,5	±0,5

Hub			tol.
diameter	B	62	±1,5
spindle hole	C	12,75	+0,15 −0
key slit			
width	E	2	±0,5
depth	U	4	±0,5
location	O	120	degrees

Amount of devices per reel

The bandolier of a 180 mm reel contains at least 3000 devices with no more than 15 empty compartments (0,5%). Three consecutive empty places might be found provided this gap is followed by 6 consecutive devices.

The carrier tape (leader) starts with at least 75 empty positions (equivalent to 300 mm); the covering foil is at least 300 mm. In order to fix the carrier tape a self-adhesive tape of 20 to 50 mm is applied.

At the end of the bandolier (trailer) at least 75 empty positions (equivalent to a length of 300 mm) and 300 mm foil. For fixing onto the reel a self-adhesive tape of 20 to 50 mm is applied.

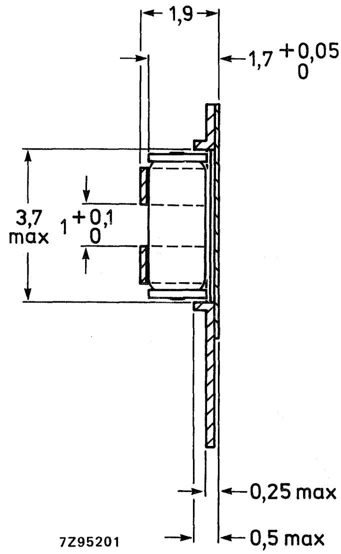


Fig. 3 Cross-sectional view of bandolier with **SOD-80** devices.

Note: Testing of **SOD-80** devices is possible in this tape. The cathode is directed towards the sprocket hole. The total number of devices per reel is 2500 for **SOD-80** and 2000 for **SOD-87.**

Semiconductors in SOT-89 encapsulations can also be delivered in reel packing for automatic placement on hybrid circuits and printed circuit boards. The devices are placed with the mounting side downwards in compartments. Total number of devices per reel is 1000.

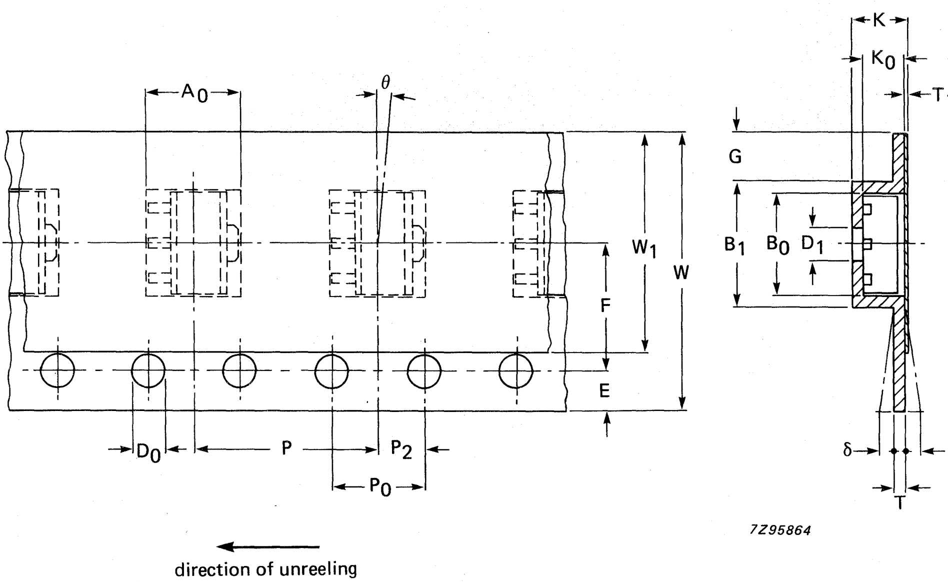


Fig. 4 Configuration of bandolier. Dimensions in mm.

Compartment			tol.
length	A_0 component length		
width	B_0 component width		
depth	K_0 component depth		
width outside	B_1	5,7	max.
pitch	P	8,0	± 0,1
deviation	Θ	± 5°	max.
hole diam.	D_1	1,5	min.
Sprocket hole			
diameter	D_0	1,5	+ 0,1
pitch	P_0	4,0	± 0,1
distance	E	1,75	± 0,1
cumulative (10) pitch error		± 0,1	

Centre line dimensions			tol.
length direction	P_2	2,0	± 0,05
width direction	F	5,5	± 0,1
Fixing tape			
width	W_1	9,5	max.
thickness	T_1	0,1	max.
Carrier tape			
width	W	12	± 0,2
bending	δ	0,3	max.
thickness	T	0,4	max.
Overall thickness	K	2,4	max.
distance	G	1,8	min.

SOLDERING RECOMMENDATIONS
SOD80, SOD87, SOT-23, SOT143 AND SOT-89 ENVELOPES

SOT-23, SOT-143 and SOT-89 devices are ideally suited for placement onto thick and thin film substrates and printed circuit boards.

To assure reliable and consistent connections particular attention should be paid to:

1. **Flux**

   A non-active flux is recommended. Where active fluxes are employed, great care in subsequent substrate cleaning must be exercised.

2. **Metal-alloy solder or solder paste**

   Correct choice of solder alloy or solder paste to be employed e.g. 62% Sn, 36% Pb, 2% Ag or 60% Sn/40% Pb. Any paste used should contain at least 85% metal dry weight.

3. **Soldering temperature**

   This will vary according to the actual method employed.

REFLOW SOLDERING

The preferred technique for mounting microminiature components on hybrid thick and thin-film is the method of reflow soldering.

The tags of SOT-23, SOT-143 and SOT-89 envelopes are pre-tinned and the best results are obtained if a similar solder is applied to the corresponding soldering areas on the substrate. This can be done by either dipping the substrate in a solder bath or by screen printing a solder paste.
The maximum temperature of the leads or tab during the soldering cycle should not exceed 285 ^{o}C.
The most economic method of soldering is a process in which all different components are soldered simultaneously for example SOT-23, SOT-143 or SOT-89 devices, capacitors and resistors.

Having first been fluxed, all components are positioned on the substrate. The slight adhesive force of the flux is sufficient to keep the components in place. Solder paste contains a flux and has therefore good inherent adhesive properties which eases positioning of the components.

With the components in position the substrate is heated to a point where the solder begins to flow. This can be done on a heating plate or on a conveyor belt running through an infrared tunnel. The maximum allowed temperature of the plastic body of a device must be kept below 280 ^{o}C during the soldering cycle. For further temperature behaviour during the soldering process see Figs 2 and 3.

The surface tension of the liquid solder tends to draw the tags of the device towards the centre of the soldering area and has thus a correcting effect on slight mispositionings. However, if the layout leaves something to be desired the same effect can result in undesirable shifts; particularly if the soldering areas on the substrate and the components are not concentrally arranged. This problem can be solved using a standard contact pattern, which leaves sufficient scope for the self-positioning effect (see Figs 4 and 5).

After cooling the connections may be visually inspected and, where necessary, repaired with a light soldering iron. Finally any remaining flux must be removed carefully.

WAVE SOLDERING

The normal (dual) wave soldering process can also be applied to SOD-80, SOT-23, SOD-87 and SOT-143 envelopes. We do not recommend SOT-89 for wave soldering.

IMMERSION SOLDERING

Where a complete substrate or printed circuit board is immersed in solder:
a. The temperature of the soldering bath should not exceed 280 °C.
b. The duration of the soldering cycle should not exceed 10 seconds.
c. Forced cooling may be applied (see Fig. 1).

HAND SOLDERING

It is possible to solder microminiature devices with a light hand-held soldering iron, but this method has obvious drawbacks and should therefore be restricted to laboratory use and/or incidental repairs on production circuits.

1. It is time-consuming and expensive.
2. The device cannot be positioned accurately and therefore the connecting tags may come into contact with the substrate and damage it.
3. There is a great risk of breaking either substrate or even internal connections inside the encapsulation.
4. The envelope may be damaged by the iron.

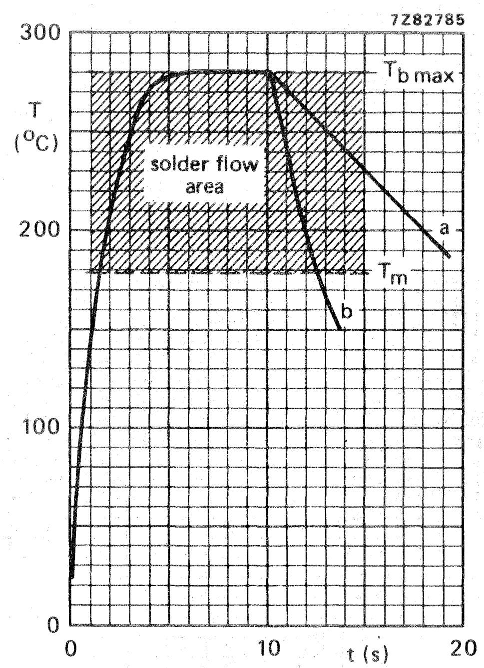
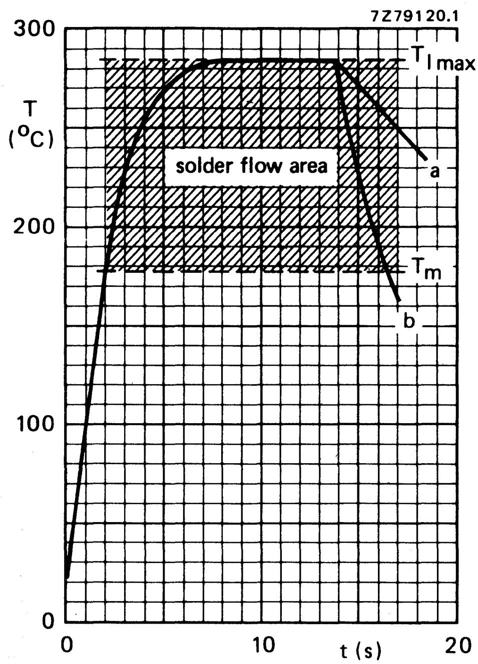


Fig. 1 Device temperature during *immersion* soldering.

Maximum time of immersion in soldering bath is 10 seconds at an ambient temperature of 25 °C.
a = free convection cooling; b = forced cooling.
$T_{b\,max}$ = maximum bath temperature (280 °C).
T_m = melting temperature of solder (179 °C).



a = free convection cooling.

b = permissible forced cooling.

$T_{l\,max}$ = Maximum lead or tab temperature = 285 °C.

T_m = Melting point of the solder is 179 °C.

T_{amb} = 25 °C.

Time of heat supply:
without preheating max. 14 s
with preheating max. 10 s

Maximum time of preheating 45 s

Fig. 2 Reflow soldering without preheating.

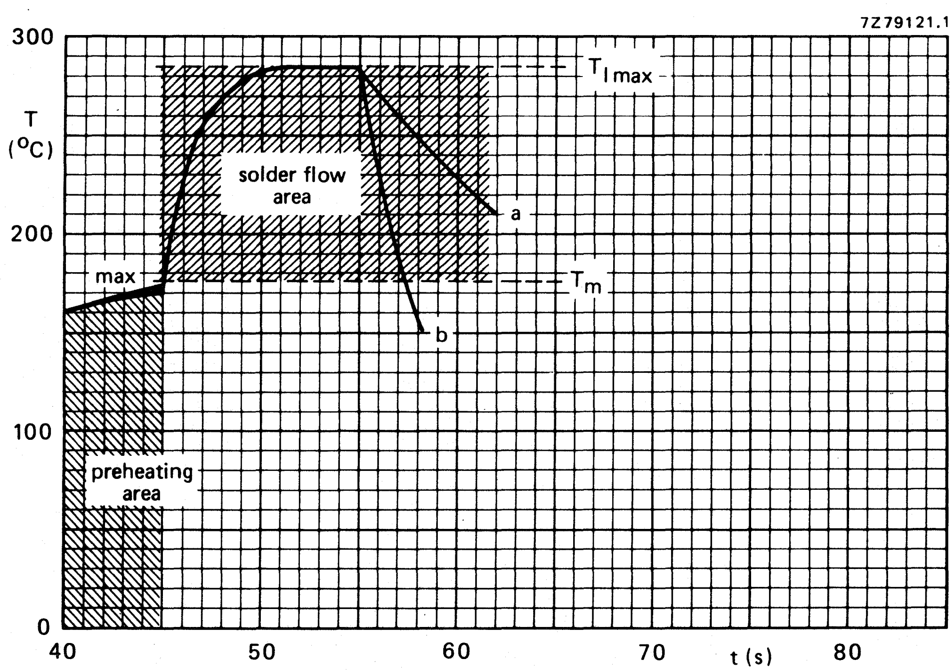


Fig. 3 Reflow soldering with preheating.

Minimum required dimensions of metal connection pads on hybrid thick and thin-film substrates.

Dimensions in mm

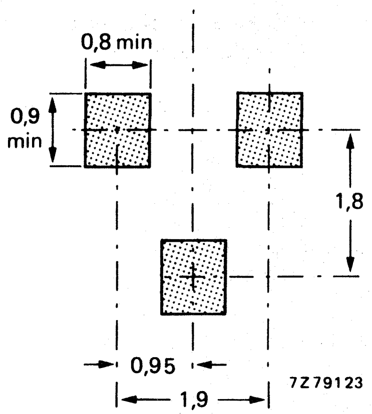


Fig. 4 SOT-23 pattern.

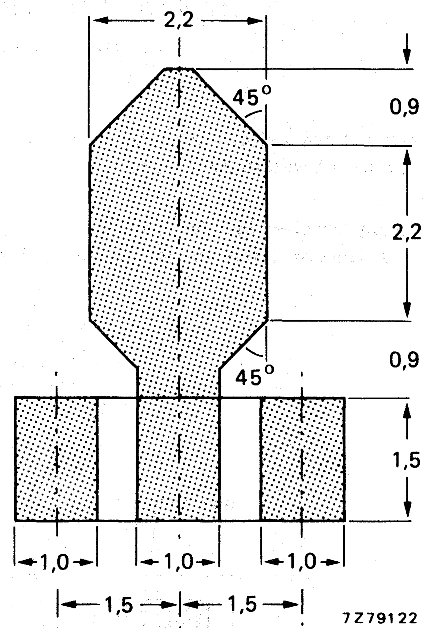


Fig. 5 SOT-89 pattern.

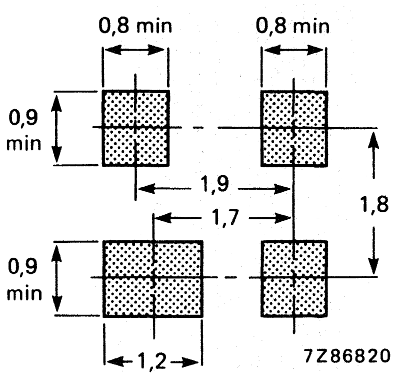


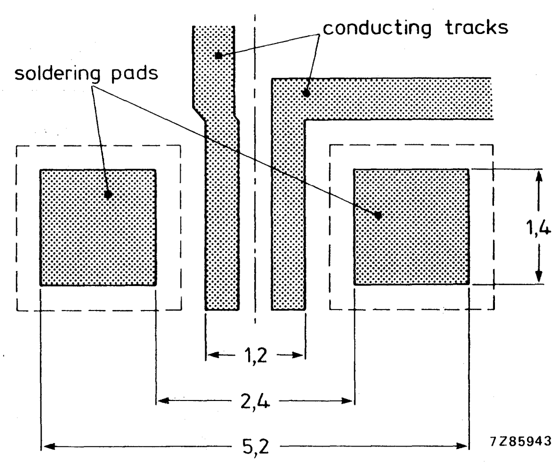
Fig. 6 SOT-143 pattern.

SOLDERING RECOMMENDATIONS
SOD-80 ENVELOPE

The layout shown below is intended for use with mounting of diodes having a SOD-80 envelope onto a printed circuit board in those cases where the diode is glued to the p.c. board first and soldered afterwards.

The dimensions given may be smaller if the diode in question is not fixed to the substrate prior to soldering. The position of the SOD-80 device is then self-adjusted during the soldering process.

Dimensions in mm



THERMAL CHARACTERISTICS
FOR SOT-23 AND SOT-143 ENVELOPES

The heat generated in a semiconductor chip normally flows by various paths to the surroundings (ambient).

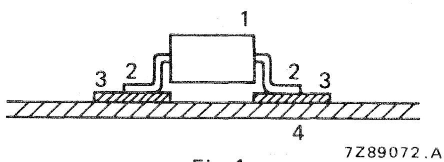


Fig. 1.

1. Heat radiation from the envelope to ambient (1).
   This heat transfer can be neglected when the envelope is mounted on a substrate or printed circuit board.
2. Heat transmission via leads (2) soldering points (3) and substrate (4).

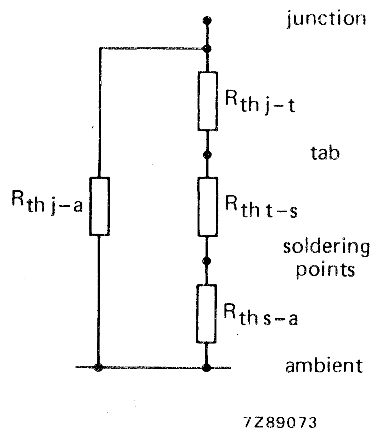


Fig. 2 Thermal behaviour of heat flow when the device is mounted on a substrate or printed circuit board.

$R_{th\ j\text{-}t}$ = Thermal resistance from junction to tab.

$R_{th\ t\text{-}s}$ = Thermal resistance from tab to soldering points.

$R_{th\ s\text{-}a}$ = Thermal resistance from soldering points to ambient.

$R_{th\ j\text{-}a}$ = Thermal resistance from junction to ambient.

Heat transfer directly from envelope to ambient

This depends on the difference between the temperatures of envelope and the surroundings. When the device is mounted on a substrate or printed circuit board direct heat flow can usually be neglected in relation to the heat flow via leads and substrate.
Thus the thermal model can be as in Fig. 3.

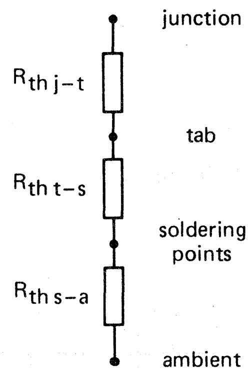


Fig. 3 Basic thermal model.

Heat transfer from junction to tab

This is an internal heat transfer and has been measured. In general it is:

for high-frequency transistors, low-power diodes and (MOS) FETs	60 K/W
for low-frequency and switching transistors	50 K/W
for low-frequency medium-power transistors	30 K/W

Heat transfer from tab to soldering points

This value has also been measured for SOT-23 with $P_{tot} < 350$ mW	280 K/W
for types of semiconductors in this envelope with $P_{tot} < 425$ mW	260 K/W
for types of semiconductors in a SOT-143 envelope this value is	310 K/W

Heat transfer from soldering points to ambient

This depends on the shape and material of tracks and substrate. In figures 4 and 5 standard mounting conditions are given to set up the maximum power ratings for SOT-23 and SOT-143 encapsulations.

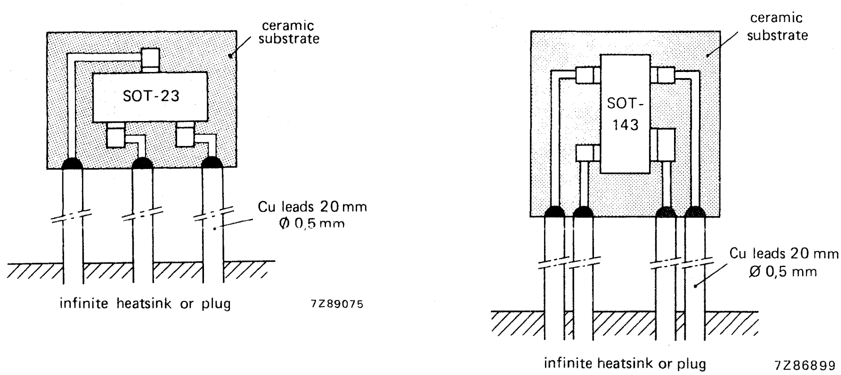


Fig. 4 Test circuits SOT-23 and SOT-143 mounting conditions on a ceramic substrate.

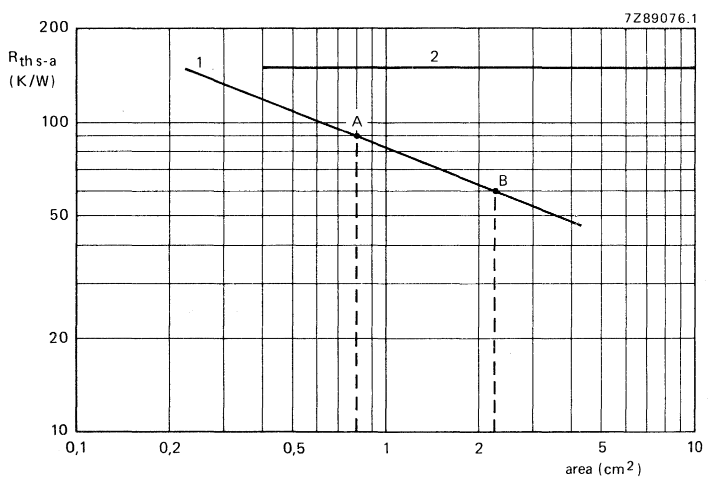


Fig. 5 Heat transfer from soldering points to ambient.

1. Ceramic substrate

Point A on the curve in Fig. 5 is for an area of the ceramic substrate of 8 mm x 10 mm x 0,7 mm for the maximum rating of all high-frequency, low-frequency and switching transistors and also for all diodes.
Point B on the curve in Fig. 5 is for an area of the ceramic substrate of 15 mm x 15 mm x 0,7 mm for the maximum rating of low-frequency medium-power semiconductors.

2. Printed circuit board

$R_{th\ s\text{-}a}$ = 150 K/W for SOT-23 and SOT-143 envelopes mounted on a printed circuit board.

The values for the thermal resistance from junction to tab, and tab to soldering points, are given earlier and in Fig. 5.
The formula for devices in SOT-23 with one crystal can be generalized:

$T_j = P\,(R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

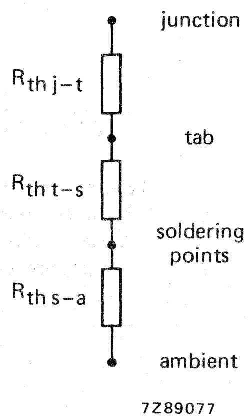


Fig. 6 Thermal model of SOT-23 envelopes with one crystal.

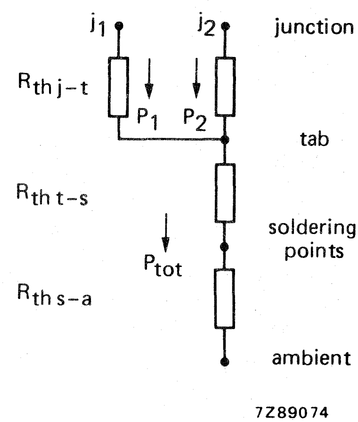


Fig. 7 Thermal model of SOT-23 envelopes with two crystals (double diode).

The formulae for devices with two crystals (double diodes) are:

$T_{tab} = P_{tot} \cdot (R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb} = P_{tot}\,(280 + 90) + T_{amb}$

$T_{j1} = (P_1 \times R_{th\ j\text{-}t}) + T_{tab} = P_1 \cdot 60 + T_{tab}$

$T_{j2} = (P_2 \times R_{th\ j\text{-}t}) + T_{tab} = P_2 \cdot 60 + T_{tab}$

As mentioned with Fig. 3:

$R_{th\ j\text{-}t}$ for diodes is 60 K/W.

$R_{th\ s\text{-}a}$ (area 8 mm x 10 mm x 0,7 mm) = 90 K/W.

$R_{th\ t\text{-}s}$ for all semiconductors in SOT-23 = 280 K/W.

Thus:

$T_{j1} = 60\,P_1 + 370\,P_{tot} + T_{amb}$.

$T_{j2} = 60\,P_2 + 370\,P_{tot} + T_{amb}$.

GENERAL

Type designation
Rating systems
Letter symbols
s-parameters

PRO ELECTRON TYPE DESIGNATION CODE FOR SEMICONDUCTOR DEVICES

This type designation code applies to discrete semiconductor devices – as opposed to integrated circuits –, multiples of such devices and semiconductor chips.

"Although not all type numbers accord with the Pro Electron system, the following explanation is given for the ones that do."

A basic type number consists of:

TWO LETTERS FOLLOWED BY A SERIAL NUMBER

FIRST LETTER

The first letter gives information about the material used for the active part of the devices.

A. GERMANIUM or other material with band gap of 0,6 to 1,0 eV.
B. SILICON or other material with band gap of 1,0 to 1,3 eV.
C. GALLIUM-ARSENIDE or other material with band gap of 1,3 eV or more.
R. COMPOUND MATERIALS (e.g. Cadmium-Sulphide).

SECOND LETTER

The second letter indicates the function for which the device is primarily designed.

A. DIODE; signal, low power
B. DIODE; variable capacitance
C. TRANSISTOR; low power, audio frequency ($R_{th\ j\text{-}mb} > 15$ K/W)
D. TRANSISTOR; power, audio frequency ($R_{th\ j\text{-}mb} \leqslant 15$ K/W)
E. DIODE; tunnel
F. TRANSISTOR; low power, high frequency ($R_{th\ j\text{-}mb} > 15$ K/W)
G. MULTIPLE OF DISSIMILAR DEVICES – MISCELLANEOUS; e.g. oscillator
H. DIODE; magnetic sensitive
L. TRANSISTOR; power, high frequency ($R_{th\ j\text{-}mb} \leqslant 15$ K/W)
N. PHOTO-COUPLER
P. RADIATION DETECTOR; e.g. high sensitivity phototransistor
Q. RADIATION GENERATOR; e.g. light-emitting diode (LED)
R. CONTROL AND SWITCHING DEVICE; e.g. thyristor, low power ($R_{th\ j\text{-}mb} > 15$ K/W)
S. TRANSISTOR; low power, switching ($R_{th\ j\text{-}mb} > 15$ K/W)
T. CONTROL AND SWITCHING DEVICE; e.g. thyristor, power ($R_{th\ j\text{-}mb} \leqslant 15$ K/W)
U. TRANSISTOR; power, switching ($R_{th\ j\text{-}mb} \leqslant 15$ K/W)
X. DIODE: multiplier, e.g. varactor, step recovery
Y. DIODE; rectifying, booster
Z. DIODE; voltage reference or regulator (transient suppressor diode, with third letter **W**)

SERIAL NUMBER

Three figures, running from 100 to 999, for devices primarily intended for consumer equipment.*
One letter (Z, Y, X, etc.) and two figures, running from 10 to 99, for devices primarily intended for industrial/professional equipment.*
This letter has no fixed meaning except W, which is used for transient suppressor diodes.

VERSION LETTER

It indicates a minor variant of the basic type either electrically or mechanically. The letter never has a fixed meaning, except letter R, indicating reverse voltage, e.g. collector to case or anode to stud.

SUFFIX

Sub-classification can be used for devices supplied in a wide range of variants called associated types. Following sub-coding suffixes are in use:

1. VOLTAGE REFERENCE and VOLTAGE REGULATOR DIODES: *ONE LETTER and ONE NUMBER*
   The LETTER indicates the nominal tolerance of the Zener (regulation, working or reference) voltage
   A. 1% (according to IEC 63: series E96)
   B. 2% (according to IEC 63: series E48)
   C. 5% (according to IEC 63: series E24)
   D. 10% (according to IEC 63: series E12)
   E. 20% (according to IEC 63: series E6)
   The number denotes the typical operating (Zener) voltage related to the nominal current rating for the whole range.
   The letter 'V' is used instead of the decimal point.

2. TRANSIENT SUPPRESSOR DIODES: *ONE NUMBER*
   The NUMBER indicates the maximum recommended continuous reversed (stand-off) voltage V_R. The letter 'V' is used as above.

3. CONVENTIONAL and CONTROLLED AVALANCHE RECTIFIER DIODES and THYRISTORS: *ONE NUMBER*
   The NUMBER indicates the rated maximum repetitive peak reverse voltage (V_{RRM}) or the rated repetitive peak off-state voltage (V_{DRM}), whichever is the lower. Reversed polarity is indicated by letter R, immediately after the number.

4. RADIATION DETECTORS: *ONE NUMBER,* preceded by a hyphen (–)
   The NUMBER indicates the depletion layer in μm. The resolution is indicated by a version LETTER.

5. ARRAY OF RADIATION DETECTORS and GENERATORS: *ONE NUMBER,* preceded by a stroke (/).
   The NUMBER indicates how many basic devices are assembled into the array.

* When these serial numbers are exhausted the serial number for consumer types may be extended to four figures, and that for industrial types to three figures.

RATING SYSTEMS

The rating systems described are those recommended by the International Electrotechnical Commission (IEC) in its Publication 134.

DEFINITIONS OF TERMS USED

Electronic device. An electronic tube or valve, transistor or other semiconductor device.

Note
This definition excludes inductors, capacitors, resistors and similar components.

Characteristic. A characteristic is an inherent and measurable property of a device. Such a property may be electrical, mechanical, thermal, hydraulic, electro-magnetic, or nuclear, and can be expressed as a value for stated or recognized conditions. A characteristic may also be a set of related values, usually shown in graphical form.

Bogey electronic device. An electronic device whose characteristics have the published nominal values for the type. A bogey electronic device for any particular application can be obtained by considering only those characteristics which are directly related to the application.

Rating. A value which establishes either a limiting capability or a limiting condition for an electronic device. It is determined for specified values of environment and operation, and may be stated in any suitable terms.

Note
Limiting conditions may be either maxima or minima.

Rating system. The set of principles upon which ratings are established and which determine their interpretation.

Note
The rating system indicates the division of responsibility between the device manufacturer and the circuit designer, with the object of ensuring that the working conditions do not exceed the ratings.

ABSOLUTE MAXIMUM RATING SYSTEM

Absolute maximum ratings are limiting values of operating and environmental conditions applicable to any electronic device of a specified type as defined by its published data, which should not be exceeded under the worst probable conditions.

These values are chosen by the device manufacturer to provide acceptable serviceability of the device, taking no responsibility for equipment variations, environmental variations, and the effects of changes in operating conditions due to variations in the characteristics of the device under consideration and of all other electronic devices in the equipment.

The equipment manufacturer should design so that, initially and throughout life, no absolute maximum value for the intended service is exceeded with any device under the worst probable operating conditions with respect to supply voltage variation, equipment component variation, equipment control adjustment, load variations, signal variation, environmental conditions, and variations in characteristics of the device under consideration and of all other electronic devices in the equipment.

DESIGN MAXIMUM RATING SYSTEM

Design maximum ratings are limiting values of operating and environmental conditions applicable to a bogey electronic device of a specified type as defined by its published data, and should not be exceeded under the worst probable conditions.

These values are chosen by the device manufacturer to provide acceptable serviceability of the device, taking responsibility for the effects of changes in operating conditions due to variations in the characteristics of the electronic device under consideration.

The equipment manufacturer should design so that, initially and throughout life, no design maximum value for the intended **service** is exceeded with a bogey device under the worst probable operating conditions with respect to supply voltage variation, equipment component variation, variation in characteristics of all other devices in the equipment, equipment control adjustment, load variation, signal variation and environmental conditions.

DESIGN CENTRE RATING SYSTEM

Design centre ratings are limiting values of operating and environmental conditions applicable to a bogey electronic device of a specified type as defined by its published data, and should not be exceeded under normal conditions.

These values are chosen by the device manufacturer to provide acceptable serviceability of the device in average applications, taking responsibility for normal changes in operating conditions due to rated supply voltage variation, equipment component variation, equipment control adjustment, load variation, signal variation, environmental conditions, and variations in the characteristics of all electronic devices.

The equipment manufacturer should design so that, initially, no design centre value for the intended service is exceeded with a bogey electronic device in equipment operating at the stated normal supply voltage.

TRANSISTOR RATINGS

The ratings are presented as voltage, current, power and temperature ratings. The list of these ratings and their definitions is given as follows:

Transistor voltage ratings

Collector to base voltage ratings

V_{CBmax} — The maximum permissible instantaneous voltage between collector and base terminals. The collector voltage is negative with respect to base in PNP transistors and positive with respect to base in NPN types.

V_{CBmax} ($I_E = 0$) — The maximum permissible instantaneous voltage between collector and base terminals, when the emitter terminal is open circuited.

Emitter to base voltage ratings

V_{EBmax} — The maximum permissible instantaneous reverse voltage between emitter and base terminal. The emitter voltage is negative with respect to base for PNP transistor and positive with respect to base for NPN types.

V_{EBmax} ($I_C = 0$) — The maximum permissible instantaneous reverse voltage between emitter and base terminals when the collector terminal is open circuited.

Collector to emitter voltage ratings

V_{CEmax} — The maximum permissible instantaneous voltage between collector and emitter terminals. The collector voltage is negative with respect to emitter in PNP transistors and positive with respect to emitter in NPN types. This rating is very dependent on circuit conditions and collector current and it is necessary to refer to the curve of V_{CE} versus I_C for the appropriate circuit condition in order to obtain the correct rating.

V_{CEmax} (Cut-off) — The maximum permissible instantaneous voltage between collector and emitter terminals when the emitter current is reduced to zero by means of a reverse emitter base voltage, i.e. the base voltage is normally positive with respect to emitter for PNP transistor and negative with respect to emitter for NPN types.

NOTE: The term "cut-off" is sometimes replaced by $V_{BE} > x$ volts, or $\frac{R_B}{R_E} \leqslant y$ which are equivalent conditions under which the device may be cut-off.

V_{CEmax} ($I_C = x$ mA) — The maximum permissible instantaneous voltage between collector and emitter terminals when the collector current is at a high value, often the max. rated value.

V_{CEmax} ($I_B = 0$) — The maximum permissible instantaneous voltage between collector and emitter terminals when the base terminal is open circuited or when a very high resistance is in series with the base terminal. Special care must be taken to ensure that thermal runaway due to excessive collector leakage current does not occur in this condition.

Due to the current dependency of V_{CE} it is usual to present this information as a voltage rating chart which is a curve of collector current versus collector to emitter voltage (see Fig. 1).

This curve is divided into two areas:

A permissible area of operation under all conditions of base drive provided the dissipation rating is not exceeded (area 1) and an area where operation is allowable under certain specified conditions (area 2). To assist in determining the rating in this second area, further curves are provided relating the voltage rating to external circuit conditions, for example:

$$\frac{R_B}{R_E},\ R_B,\ Z_{Bg},\ V_{BE},\ I_B \text{ or } \frac{V_{BB}}{R_B}.$$

An example of this type of curve is given in Fig. 2 as V_{CE} versus $\frac{R_B}{R_E}$ for two different values of collector current.

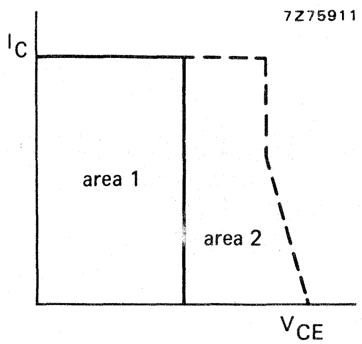


Fig. 1.

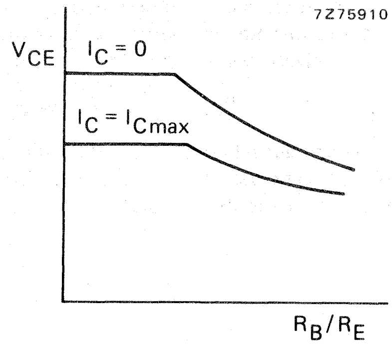


Fig. 2.

It should be noted that when R_E is shunted by a capacitor, the collector voltage V_{CE} during switching must be restricted to a value which does not rely on the effect of R_E.
In the case of an inductive load and when an energy rating is given, it may be permissible to operate outside the rated area provided the spcified energy rating is not exceeded.

Transistor current ratings

Collector current ratings

I_{Cmax}	The maximum permissible collector current. Without further qualification, the d.c. value is implied.
$I_{C(AV)max}$	The maximum permissible average value of the total collector current
I_{CM}	The maximum permissible instantaneous value of the total collector current.

Emitter current ratings

I_{Emax}	The maximum permissible emitter current. Without further qualification, the d.c. value is implied.
$I_{E(AV)max}$	The maximum permissible average value of the total emitter current.
$I_{ER(AV)max}$	The maximum permissible average value of the total emitter current when operating in the reverse emitter-base breakdown region.
I_{EM}	The maximum permissible instantaneous value of the total emitter current.
I_{ERM}	The maximum permissible instantaneous value of the total reverse emitter current allowable in the reverse breakdown region.

Base current ratings

I_{Bmax}	The maximum permissible base current. Without further qualification, the d.c. value is implied.
$I_{B(AV)max}$	The maximum permissible average value of the total base current.
$I_{BR(AV)max}$	The maximum permissible average value of the total reverse base current allowable in the reverse breakdown region.
I_{BM}	The maximum permissible instantaneous value of the total base current. The rating also includes the switch off current.
I_{BRM}	The maximum permissible instantaneous value of the total reverse current allowable in the reverse breakdown region.

Transistor power ratings

P_{tot} max: The total maximum permissible continuous power dissipation in the transistor and includes both the collector-base dissipation and the emitter-base dissipation. Under steady state conditions the total power is given by the expression:

$$P_{tot} = V_{CE} \times I_C + V_{BE} \times I_B.$$

In order to distinguish between "steady state" and "pulse" conditions the terms "steady state power (P_S)" and "pulse power (P_P)" are often used. The permissible total power dissipation is dependent upon temperature and its relationship is shown by means of a chart as shown in Fig. 3.

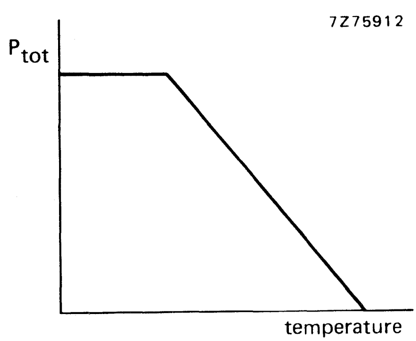


Fig. 3.

The temperature may be ambient, case or mounting base temperatures. Where a cooling clip or a heatsink is attached to the device, the allowable power dissipation is also dependent on the efficiency of the heatsink.

The efficiency of this clip or heatsink is measured in terms of its thermal resistance ($R_{th\ h}$) normally expressed in degrees kelvin per watt (K/W). For mounting base rated devices, the added effect of the contact resistance ($R_{th\ i}$) must be taken into account.

The effect of heatsinks of various thermal resistance and contact resistance is often included in the above chart.

Thus for any heatsink of known thermal resistance and any given ambient temperature, the maximum permissible power dissipation can be established. Alternatively, knowing the power dissipation which will occur and the ambient temperature, the necessary heatsink thermal resistance can be calculated.

A general expression from which the total permissible steady state power dissipation can be calculated is:

$$P_{tot} = \frac{T_j - T_{amb}}{R_{th\ j\text{-}a}}$$

where $R_{th\ j\text{-}a}$ is the thermal resistance from the transistor junction to the ambient. For case rated or mounting base rated devices, the thermal resistance $R_{th\ j\text{-}a}$ is made up of the thermal resistance junction to case or mounting base ($R_{th\ j\text{-}mb}$), the contact thermal resistance ($R_{th\ i}$) and the heatsink thermal resistance $R_{th\ h}$.

For the calculation of pulse power operation P_p, the maximum pulse power is obtained by the aid of a chart as shown in Fig. 4.

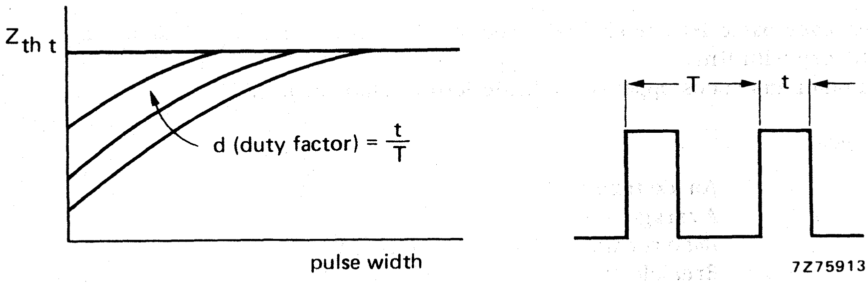


Fig. 4.

The general expression from which the maximum pulse power dissipation can be calculated is:

$$P_p = \frac{T_j - T_{amb} - P_s \times R_{th\ j\text{-}a}}{Z_{th\ t} + d\ (R_{th\ c\text{-}a})}$$

where $Z_{th\ t}$ and d are given in the above chart and $R_{th\ c\text{-}a}$ is the thermal resistance between case and ambient for case rated device. For mounting base rated device, it is equal to $R_{th\ h} + R_{th\ i}$ and is zero for free air rated device because the effect of the temperature rise of the case over the ambient for a pulse train is already included in $Z_{th\ t}$.

Temperature ratings

T_{jmax}	The maximum permissible junction temperature which is used as the basis for the calculation of power ratings. Unless otherwise stated, the continuous value is implied.
T_{jmax} (continous operation)	The maximum permissible continuous value.
T_{jmax} (intermittent operation)	The maximum permissible instantaneous junction temperature usually allowed for a total duration of 200 hours.
T_{mb}	The temperature of the surface making contact with a heatsink. This is confined to devices where a flange or stud for fixing onto a heatsink forms an integral part of the envelope.
T_{case}	The temperature of the envelope. This is confined to devices to which may be attached a clip-on cooling fin.

LETTER SYMBOLS FOR TRANSISTORS AND SIGNAL DIODES

based on IEC Publication 148

LETTER SYMBOLS FOR CURRENTS, VOLTAGES AND POWERS

Basic letters

The basic letters to be used are:

I, i = current
V, v = voltage
P, p = power.

Lower-case basic letters shall be used for the representation of instantaneous values which vary with time.
In all other instances upper-case basic letters shall be used.

Subscripts

A, a	Anode terminal
(AV), (av)	Average value
B, b	Base terminal, for MOS devices: Substrate
(BR)	Breakdown
C, c	Collector terminal
D, d	Drain terminal
E, e	Emitter terminal
F, f	Forward
G, g	Gate terminal
K, k	Cathode terminal
M, m	Peak value
O, o	As third subscript: The terminal not mentioned is open circuited
R, r	As first subscript: Reverse. As second subscript: Repetitive. As third subscript: With a specified resistance between the terminal not mentioned and the reference terminal.
(RMS), (rms)	R.M.S. value
S, s	As first or second subscript: Source terminal (for FETS only) As second subscript: Non-repetitive (not for FETS) As third subscript: Short circuit between the terminal not mentioned and the reference terminal
X, x	Specified circuit
Z, z	Replaces R to indicate the actual working voltage, current or power of voltage reference and voltage regulator diodes.

Note: No additional subscript is used for d.c. values.

Upper-case subscripts shall be used for the indication of:

a) continuous (d.c.) values (without signal)

Example I_B

b) instantaneous total values

Example i_B

c) average total values

Example $I_{B(AV)}$

d) peak total values

Example I_{BM}

e) root-mean-square total values

Example $I_{B(RMS)}$

Lower-case subscripts shall be used for the indication of values applying to the varying component alone:

a) instantaneous values

Example i_b

b) root-mean-square values

Example $I_{b(rms)}$

c) peak values

Example I_{bm}

d) average values

Example $I_{b(av)}$

Note: If more than one subscript is used, subscript for which both styles exist shall either be all upper-case or all lower-case.

Additional rules for subscripts

Subscripts for currents

Transistors: If it is necessary to indicate the terminal carrying the current, this should be done by the first subscript (conventional current flow from the external circuit into the terminal is positive).

Examples: I_B, i_B, i_b, I_{bm}

Diodes: To indicate a forward current (conventional current flow into the anode terminal) the subscript F or f should be used; for a reverse current (conventional current flow out of the anode terminal) the subscript R or r should be used.

Examples: I_F, I_R, i_F, $I_{f(rms)}$

Subscripts for voltages

Transistors: If it is necessary to indicate the points between which a voltage is measured, this should be done by the first two subscripts. The first subscript indicates the terminal at which the voltage is measured and the second the reference terminal or the circuit node. Where there is no possibility of confusion, the second subscript may be omitted.

Examples: V_{BE}, v_{BE}, v_{be}, V_{bem}

Diodes: To indicate a forward voltage (anode positive with respect to cathode), the subscript F or f should be used; for a reverse voltage (anode negative with respect to cathode) the subscript R or r should be used.

Examples: V_F, V_R, v_F, V_{rm}

Subscripts for supply voltages or supply currents

Supply voltages or supply currents shall be indicated by repeating the appropriate terminal subscript.

Examples: V_{CC}, I_{EE}

Note: If it is necessary to indicate a reference terminal, this should be done by a third subscript

Example : V_{CCE}

Subscripts for devices having more than one terminal of the same kind

If a device has more than one terminal of the same kind, the subscript is formed by the appropriate letter for the terminal followed by a number; in the case of multiple subscripts, hyphens may be necessary to avoid misunderstanding.

Examples: I_{B2} = continuous (d.c.) current flowing into the second base terminal

V_{B2-E} = continuous (d.c.) voltage between the terminals of second base and emitter

Subscripts for multiple devices

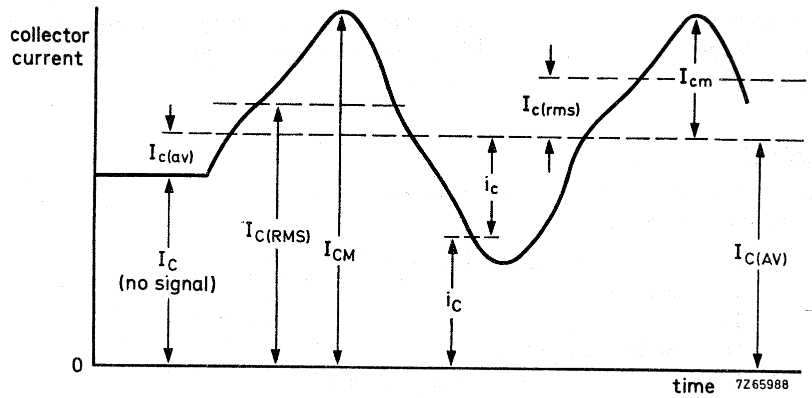
For multiple unit devices, the subscripts are modified by a number preceding the letter subscript; in the case of multiple subscripts, hyphens may be necessary to avoid misunderstanding.

Examples: I_{2C} = continuous (d.c.) current flowing into the collector terminal of the second unit

V_{1C-2C} = continuous (d.c.) voltage between the collector terminals of the first and the second unit.

Application of the rules

The figure below represents a transistor collector current as a function of time. It consists of a continuous (d.c.) current and a varying component.



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LETTER SYMBOLS FOR ELECTRICAL PARAMETERE METERS

Defenition

For the purpose of this Publication, the term "electrical parameter" applies to four-pole matrix parameters, elements of electrical equivalent circuits, electrical impedances and admittances, inductances and capacitances.

Basic letters

The following is a list of the most important basic letters used for electrical parameters of semiconductor devices.

B, b = susceptance; imaginary part of an admittance

C = capacitance

G, g = conductance; real part of an admittance

H, h = hybrid parameter

L = inductance

R, r = resistance; real part of an impedance

X, x = reactance; imaginary part of an impedance

Y, y = admittance;

Z, z = impedance;

Upper-case letters shall be used for the representation of:

a) electrical parameters of external circuits and of circuits in which the device forms only a part;

b) all inductances and capacitances.

Lower-case letters shall be used for the representation of electrical parameters inherent in the device (with the exception of inductances and capacitances).

Subscripts

General subscripts

The following is a list of the most important general subscripts used for electrical parameters of semiconductor devices:

F, f	= forward; forward transfer
I, i (or 1)	= input
L, l	= load
O, o (or 2)	= output
R, r	= reverse; reverse transfer
S, s	= source

Examples: Z_S, h_f, h_F

The upper-case variant of a subscript shall be used for the designation of static (d.c.) values.

Examples : h_{FE} = static value of forward current transfer ratio in common-emitter configuration (d.c. current gain)

R_E = d.c. value of the external emitter resistance.

Note: The static value is the slope of the line from the origin to the operating point on the appropriate characteristic curve, i.e. the quotient of the appropriate electrical quantities at the operating point.

The lower-case variant of a subscript shall be used for the designation of small-signal values.

Examples: h_{fe} = small-signal value of the short-circuit forward current transfer ratio in common-emitter configuration

$Z_e = R_e + jX_e$ = small-signal value of the external impedance

Note: If more than one subscript is used, subscripts for which both styles exist shall either be all upper-case or all lower-case

Examples: h_{FE}, y_{RE}, h_{fe}

Subscripts for four-pole matrix parameters

The first letter subscript (or double numeric subscript) indicates input, output, forward transfer or reverse transfer

Examples: h_i (or h_{11})
h_o (or h_{22})
h_f (or h_{21})
h_r (or h_{12})

A further subscript is used for the identification of the circuit configuration. When no confusion is possible, this further subscript may be omitted.

Examples: h_{fe} (or h_{21e}), h_{FE} (or h_{21E})

Distinction between real and imaginary parts

If it is necessary to distinguish between real and imaginary parts of electrical parameters, no additional subscripts should be used. If basic symbols for the real and imaginary parts exist, these may be used.

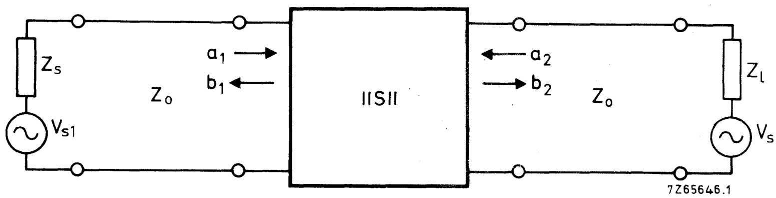
Examples: $Z_i = R_i + jX_i$
$y_{fe} = g_{fe} + jb_{fe}$

If such symbols do not exist or if they are not suitable, the following notation shall be used:

Examples: Re (h_{ib}) etc. for the real part of h_{ib}
Im (h_{ib}) etc. for the imaginary part of h_{ib}

SCATTERING PARAMETERS

In distinction to the conventional h, y and z-parameters, s-parameters relate to travelling wave conditions. The figure below shows a two-port network with the incident and reflected waves a_1, b_1, a_2 and b_2.



$$a_1 = \frac{V_{i1}}{\sqrt{Z_o}} \qquad a_2 = \frac{V_{i2}}{\sqrt{Z_o}}$$

$$b_1 = \frac{V_{r1}}{\sqrt{Z_o}} \qquad b_2 = \frac{V_{r2}}{\sqrt{Z_o}}$$ [1)]

Z_o = characteristic impedance of the transmission line in which the two-port is connected.

V_i = incident voltage

V_r = reflected (generated) voltage

The four-pole equations for s-parameters are:

$$b_1 = s_{11}a_1 + s_{12}a_2$$
$$b_2 = s_{21}a_1 + s_{22}a_2$$

Using the subscripts i for 11, r for 12, f for 21 and o for 22, it follows that:

$$s_i = s_{11} = \left.\frac{b_1}{a_1}\right|_{a_2 = 0}$$

$$s_r = s_{12} = \left.\frac{b_1}{a_2}\right|_{a_1 = 0}$$

$$s_f = s_{21} = \left.\frac{b_2}{a_1}\right|_{a_2 = 0}$$

$$s_o = s_{22} = \left.\frac{b_2}{a_2}\right|_{a_1 = 0}$$

1) The squares of these quantities have the dimension of power.

The s-parameters can be named and expressed as follows:

$s_i = s_{11}$ = Input reflection coefficient.
The complex ratio of the reflected wave and the incident wave at the input, under the conditions $Z_l = Z_o = 50\ \Omega$ and $V_{s2} = 0$.

$s_r = s_{12}$ = Reverse transmission coefficient.
The complex ratio of the generated wave at the input and the incident wave at the output, under the conditions $Z_s = Z_o = 50\ \Omega$ and $V_{s1} = 0$.

$s_f = s_{21}$ = Forward transmission coefficient.
The complex ratio of the generated wave at the output and the incident wave at the input, under the conditions $Z_l = Z_o = 50\ \Omega$ and $V_{s2} = 0$.

$s_o = s_{22}$ = Output reflection coefficient.
The complex ratio of the reflected wave and the incident wave at the output, under the conditions $Z_s = Z_o = 50\ \Omega$ and $V_{s1} = 0$.

DEVICE DATA

BAND-SWITCHING DIODES FOR SURFACE MOUNTING

Switching diodes in a SOD-80 envelope, intended for band switching in v.h.f. television tuners. A special feature of these diodes is their low capacitance.

These SM diodes are leadless diodes in an hermetically sealed micro-miniature glass envelope with tin plated metal discs at each end. They are suitable for Automatic Placement and as such they can withstand immersion soldering.

The diodes are delivered in "super 8" tape.

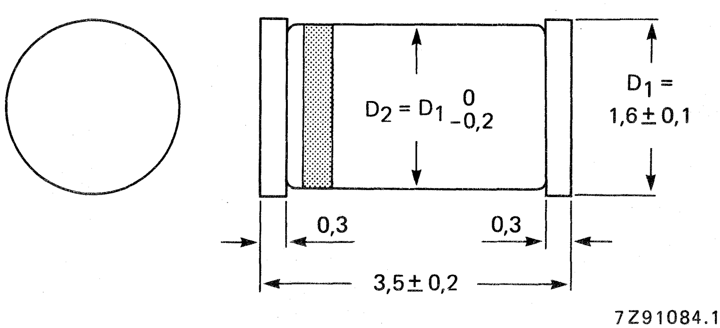
QUICK REFERENCE DATA

			BA682	BA683	
Continuous reverse voltage	V_R	max.	35	35	V
Forward current (d.c.)	I_F	max.	100	100	mA
Junction temperature	T_j	max.	150	150	°C
Diode capacitance V_R = 3 V; f = 1 MHz	C_d	<	1,25	1,2	pF
Series resistance at f = 200 MHz					
I_F = 3 mA	r_D	<	0,7	1,2	Ω
I_F = 10 mA	r_D	<	0,5	0,9	Ω

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-80.



The cathode is indicated by a red band.
The BA683 cathode has an additional orange band.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	35	V
Forward current (d.c.)	I_F	max.	100	mA
Storage temperature	T_{stg}		–65 to +150	°C
Junction temperature	T_j		150	°C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j\text{-}a}$ =	0,6	K/mW

CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

Forward voltage				
I_F = 100 mA	V_F	<	1,0	V
Reverse current				
V_R = 20 V	I_R	<	50	nA
V_R = 20 V; T_{amb} = 75 °C	I_R	<	1	μA

			BA682	BA683	
Diode capacitance at f = 1 MHz					
V_R = 1 V	C_d	<	1,5	1,5	pF
V_R = 3 V	C_d	<	1,25	1,2	pF
Series resistance at f = 200 MHz					
I_F = 3 mA	r_D	<	0,7	1,2	Ω
I_F = 10 mA	r_D	<	0,5	0,9	Ω

SILICON PLANAR EPITAXIAL HIGH-SPEED DIODE

Silicon epitaxial high-speed diode in a microminiature plastic envelope. It is intended for high-speed switching in hybrid thick and thin-film circuits.

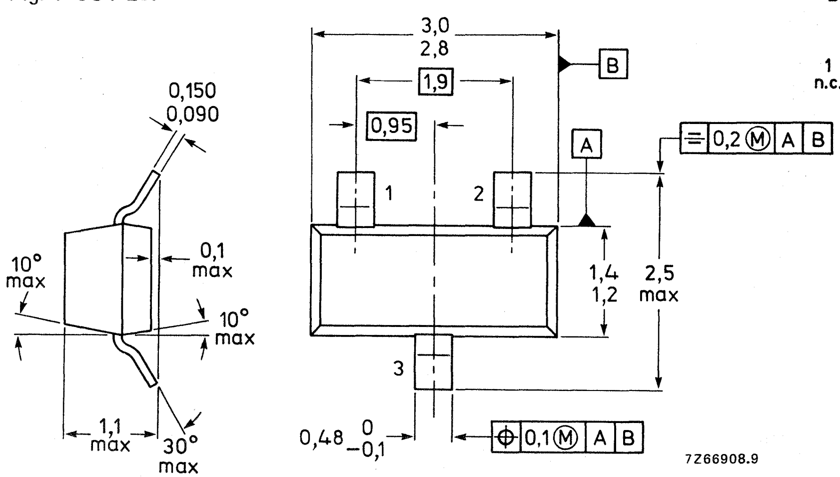
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	75	V
Repetitive peak reverse voltage	V_{RRM}	max.	85	V
Repetitive peak forward current	I_{FRM}	max.	250	mA
Junction temperature	T_j	max.	175	^oC
Forward voltage at I_F = 50 mA	V_F	<	1,0	V
Reverse recovery time when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<	6	ns
Recovery charge when switched from I_F = 10 mA to V_R = 5 V; R_L = 500 Ω	Q_s	<	45	pC

MECHANICAL DATA

Dimensions in mm

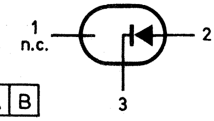
Fig. 1 SOT-23.



TOP VIEW

Marking code

BAS16 = A6



See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	75	V
Repetitive peak reverse voltage	V_{RRM}	max.	85	V
Average rectified forward current▲ (averaged over any 20 ms period) up to T_{amb} = 25 °C**	$I_{F(AV)}$	max.	250	mA
Forward current (d.c.)	I_F	max.	250	mA
Repetitive peak froward current	I_{FRM}	max.	250	mA
→ Non-repetitive peak forward current (per crystal)				
t = 1 μs	I_{FSM}	max.	2	A
t = 1 ms	I_{FSM}	max.	1	A
t = 1 s	I_{FSM}	max.	0,5	A
Storage temperature range	T_{stg}	−65 to + 175		°C
Junction temperature	T_j	max.	175	°C

THERMAL RESISTANCE*

→ From junction to ambient**	$R_{th\ j\text{-}a}$	=	430	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

Forward voltage				
I_F = 1 mA	V_F	<	715	mV
I_F = 10 mA	V_F	<	855	mV
I_F = 50 mA	V_F	<	1000	mV
I_F = 150 mA	V_F	<	1250	mV
Reverse current				
V_R = 25 V; T_j = 150 °C	I_R	<	30	μA
V_R = 75 V	I_R	<	1	μA
V_R = 75 V; T_j = 150 °C	I_R	<	50	μA
Diode capacitance V_R = 0; f = 1 MHz	C_d	<	2	pF
Forward recovery voltage (see also Fig. 2) when switched to I_F = 10 mA; t_p = 20 ns	V_{fr}	<	1,75	V
Reverse recovery time (see also Fig. 3) when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<	6	ns
Recovery charge (see also Fig. 4) when switched from I_F = 10 mA to V_R = 5 V; R_L = 500 Ω	Q_s	<	45	pC

▲ Measured under pulse conditions. $t_p \leq 0,5$ ms. $I_{F(AV)}$ = 150 mA, $t_{(av)} \leq 1$ ms, for sinusoidal operation.

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

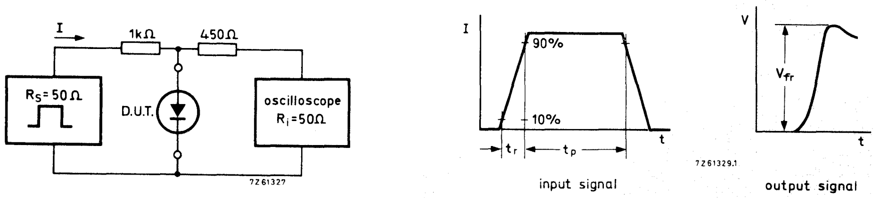


Fig. 2 Forward recovery voltage test circuit and waveforms.

Input signal: forward pulse rise time = t_r = 20 ns; forward current pulse duration t_p = 120 ns; duty factor = δ = 0,01.
Oscilloscope: rise time = t_r = 0,35 ns.
Circuit capacitance C $\leqslant$ 1 pF (C = oscilloscope input capacitance + parasitic capacitance).

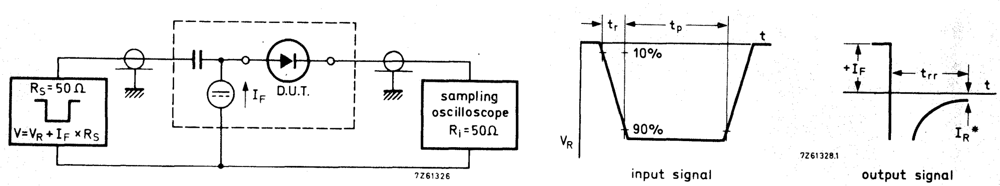


Fig. 3 Reverse recovery time test circuit and waveforms.

Input signal: reverse pulse rise time = t_r = 0,6 ns; reverse pulse duration = t_p = 100 ns; duty factor = δ = 0,05.
* t_{rr} up to I_R = 1 mA.
Oscilloscope: rise time = t_r = 0,35 ns.
Circuit capacitance C $\leqslant$ 1 pF (C = oscilloscope input capacitance + parasitic capacitance).

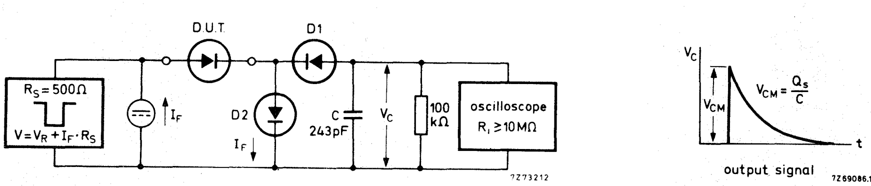


Fig. 4 Recovery charge test circuit and waveform.

D1 = BAW62; D2 = diode with minority carrier life time at 10 mA: < 200 ps
Input signal

Rise time of the reverse pulse	t_r	=	2 ns
Reverse pulse duration	t_p	=	400 ns
Duty factor	δ	=	0,02

Circuit capacitance C $\leqslant$ 7 pF (C = oscilloscope input capacitance + parasitic capacitance).

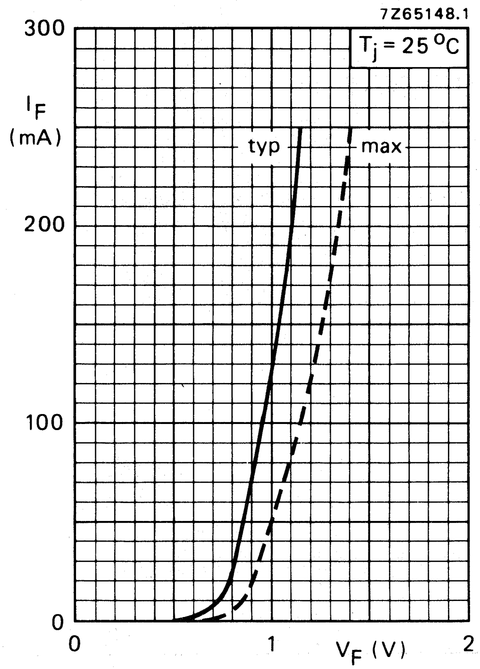


Fig. 5.

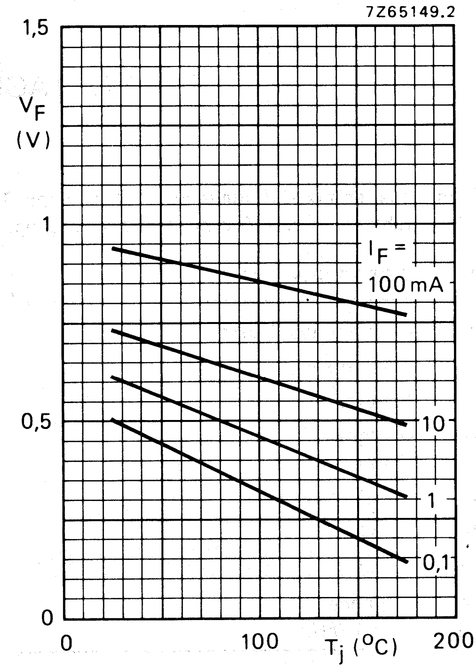


Fig. 6 Typical values.

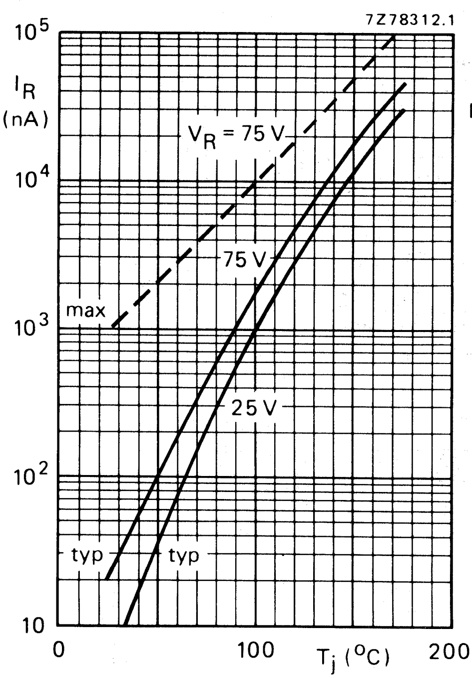


Fig. 7.

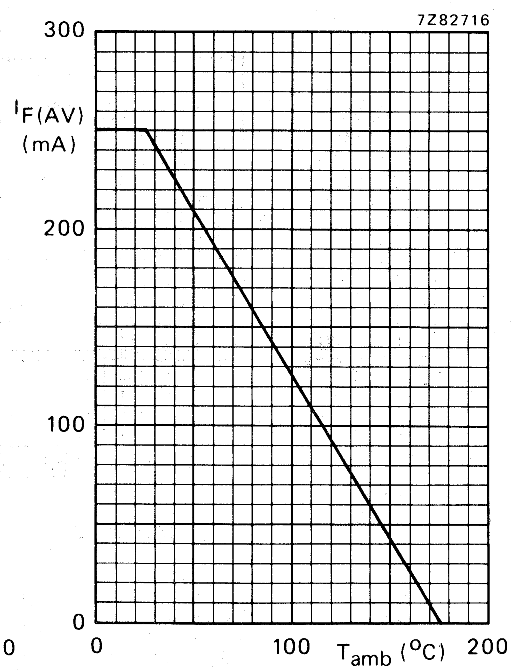


Fig. 8 Current derating curve.

LOW VOLTAGE STABISTOR

Silicon planar epitaxial diode in SOT-23 envelope. This diode is intended for low voltage stabilizing e.g. bias stabilizer in class-B output stages, clipping, clamping and meter protection.

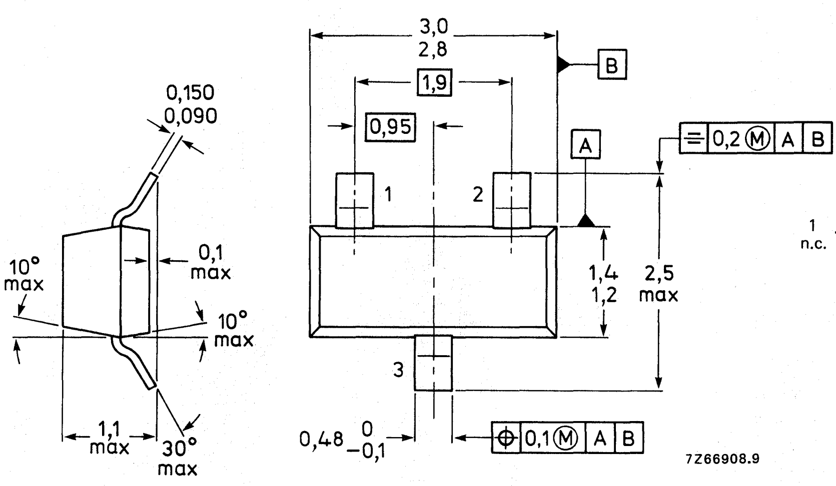
QUICK REFERENCE DATA

Repetitive peak forward current	I_{FRM}	max.	250	mA
Storage temperature	T_{stg}		−65 to + 150	°C
Junction temperature	T_j	max.	175	°C
Forward voltage				
I_F = 0,1 mA	V_F		580 to 660	mV
I_F = 1,0 mA	V_F		665 to 745	mV
I_F = 10 mA	V_F		750 to 830	mV
I_F = 100 mA	V_F		870 to 960	mV
Diode capacitance				
V_R = 0; f = 1 MHz	C_d	<	140	pF

MECHANICAL DATA

Dimensions in mm

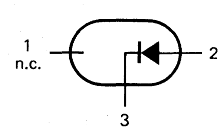
Fig. 1 SOT-23.



TOP VIEW

Marking code

BAS17 = A91



See also chapter *Soldering Recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Repetitive peak forward current **	I_{FRM}	max.	250	mA
Storage temperature	T_{stg}	−65 to + 150		°C
Junction temperature	T_j	max.	175	°C

THERMAL CHARACTERISTICS*

$T_j = Px (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	60	K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280	K/W
From soldering points to ambient**	$R_{th\ s\text{-}a}$	=	90	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltage				
I_F = 0,1 mA	V_F		580 to 660	mV
I_F = 1,0 mA	V_F		665 to 745	mV
I_F = 5,0 mA	V_F		725 to 805	mV
I_F = 10 mA	V_F		750 to 830	mV
I_F = 100 mA	V_F		870 to 960	mV
Reverse current				
V_R = 4 V	I_R	<	5	μA
Temperature coefficient				
I_F = 1 mA	S_F	typ.	−1,8	mV/K
Diode capacitance				
V_R = 0; f = 1 MHz	C_d	<	140	pF

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 7 mm x 5 mm x 0,5 mm.

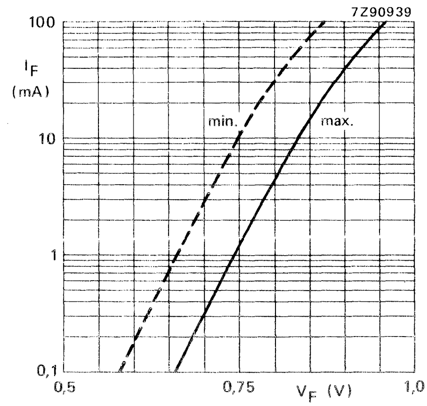


Fig. 2 Forward current as a function of forward voltage.

SILICON PLANAR EPITAXIAL HIGH-SPEED DIODES

Silicon epitaxial high-speed diodes in a microminiature plastic envelope. They are intended for switching and general purposes.

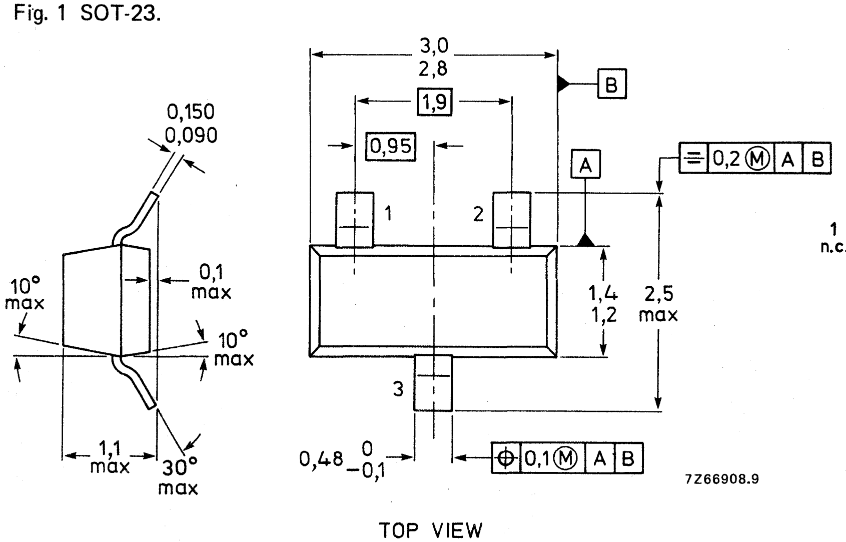
QUICK REFERENCE DATA

			BAS19	BAS20	BAS21	
Continuous reverse voltage	V_R	max.	100	150	200	V
Repetitive peak reverse voltage	V_{RRM}	max.	120	200	250	V
Repetitive peak forward current	I_{FRM}	max.		625		mA
Junction temperature	T_j	max.		150		°C
Forward voltage at I_F = 100 mA	V_F	<		1		V
Reverse recovery time when switched from I_F = 30 mA to I_R = 30 mA; R_L = 100 Ω measured at I_R = 3 mA	t_{rr}	<		50		ns

MECHANICAL DATA

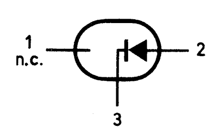
Dimensions in mm

Fig. 1 SOT-23.



Marking code

BAS19 = A8
BAS20 = A81
BAS21 = A82



See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BAS19	BAS20	BAS21	
Continuous reverse voltage	V_R	max.	100	150	200	V
Repetitive peak reverse voltage	V_{RRM}	max.	120	200	250	V
→ Non-repetitive peak forward current (per crystal)						
t = 1 μs	I_{FSM}	max.		2,5		A
t = 1 s	I_{FSM}	max.		0,5		A
Average rectified forward current (1) (averaged over any 20 ms period)	$I_{F(AV)}$	max.		200		mA
Forward current (d.c.) up to T_{amb} = 25 °C**	I_F	max.		200		mA
Repetitive peak forward current	I_{FRM}	max.		625		mA
Storage temperature range	T_{stg}			−65 to + 150		°C
Junction temperature	T_j	max.		150		°C
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.		200		mW

THERMAL RESISTANCE*

From junction to ambient**	$R_{th\,j\text{-}a}$	=	430	K/W
From tab to soldering points	$R_{th\,t\text{-}s}$	=	280	K/W
From soldering points to ambient**	$R_{th\,s\text{-}a}$	=	90	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

Forward voltage				
I_F = 100 mA	V_F	<	1,0	V
I_F = 200 mA	V_F	<	1,25	V
Reverse breakdown voltage (1)				
BAS19; I_R = 100 μA	$V_{(BR)R}$	>	120	V
BAS20; I_R = 100 μA	$V_{(BR)R}$	>	200	V
BAS21; I_R = 100 μA (2)	$V_{(BR)R}$	>	250	V
Reverse current				
$V_R = V_{Rmax}$	I_R	<	100	nA
$V_R = V_{Rmax}$; T_j = 150 °C	I_R	<	100	μA
Differential resistance				
I_F = 10 mA	r_{diff}	typ.	5	Ω

(1) Measured under pulse conditions; Pulse time = $t_p \leqslant$ 0,3 ms.
(2) At zero life time, measured under pulse conditions to avoid excessive dissipation and voltage limited to 275 V.
* See *Thermal characteristics.*
** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

Diode capacitance			
V_R = 0; f = 1 MHz	C_d	<	5 pF
Reverse recovery time (see Figs 2 and 3)			
when switched from I_F = 30 mA to I_R = 30 mA;			
R_L = 100 Ω; measured at I_R = 3 mA	t_{rr}	<	50 ns

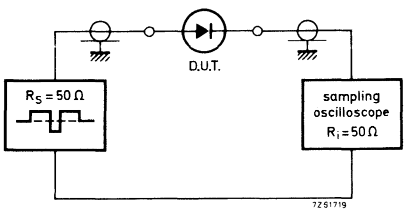


Fig. 2 Test circuit.

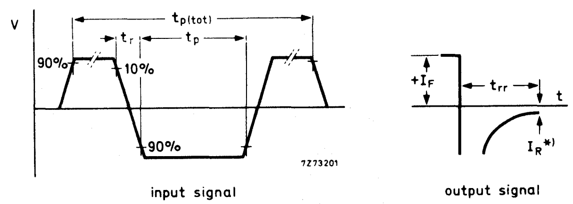


Fig. 3 Waveforms; I_R = 3 mA.

Input signal		
total pulse duration	$t_{p(tot)}$	= 2 μs
duty factor	δ	= 0,0025
rise time of reverse pulse	t_r	= 0,6 ns
reverse pulse duration	t_p	= 100 ns
Oscilloscope		
rise time	t_r	= 0,35 ns
circuit capacitance*	C	< 1 pF

*C = oscilloscope input capacitance + parasitic capacitance.

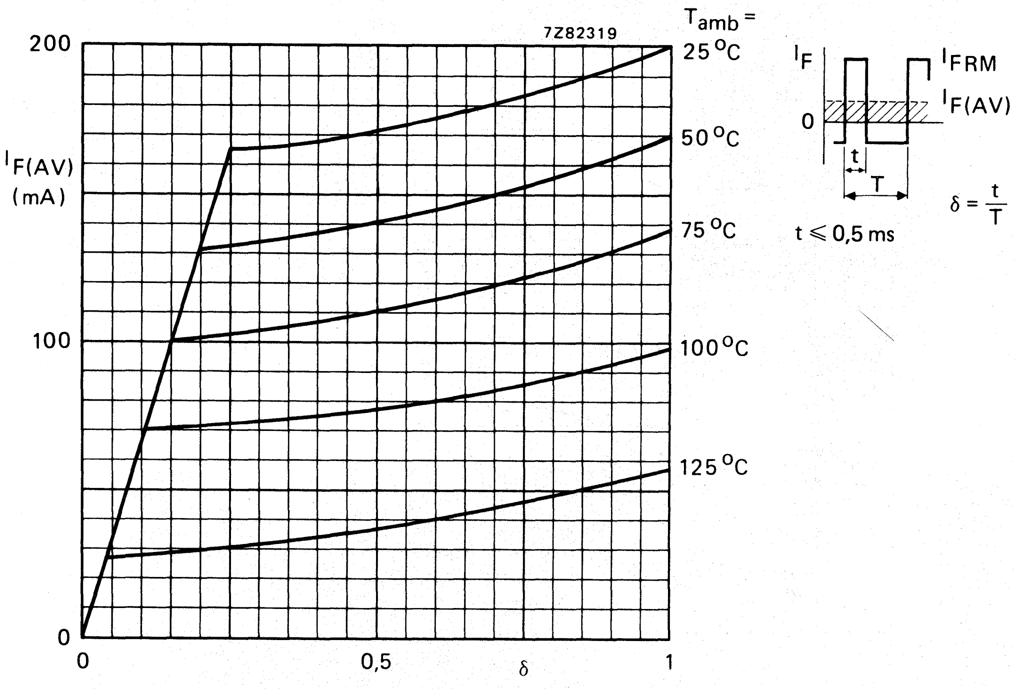


Fig. 4 BAS19; maximum permissible average rectified forward current for pulse operation as a function of the duty factor at V_R = 100 V.

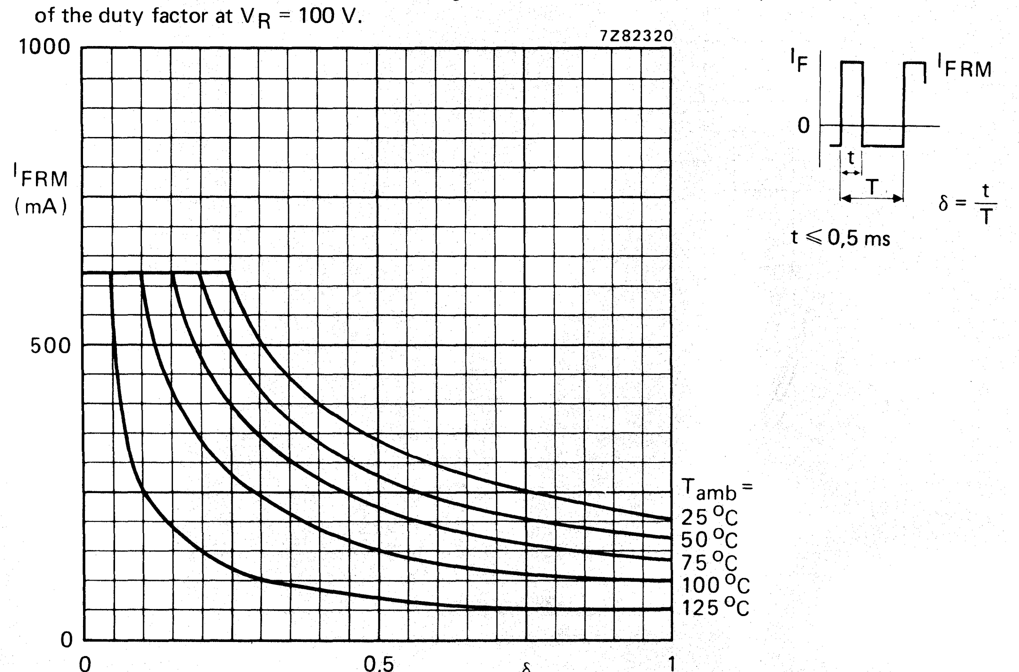


Fig. 5 BAS19; maximum permissible repetitive peak forward current for pulse operation as a function of the duty factor at V_R = 100 V.

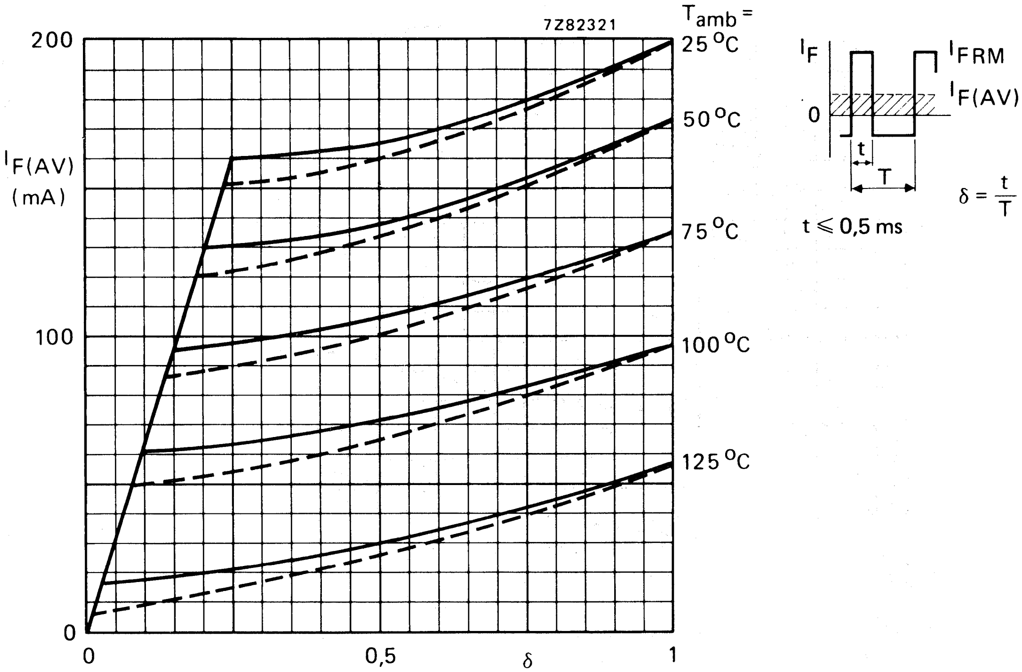


Fig. 6 BAS20/21; maximum permissible average rectified forward current for pulse operation as a function of the duty factor.

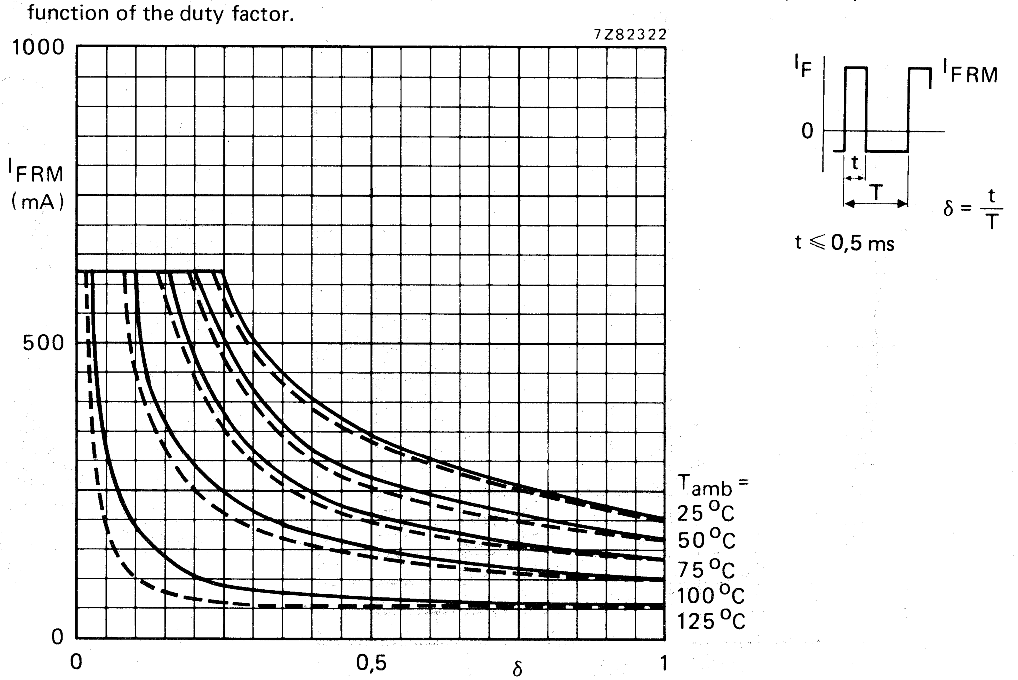


Fig. 7 BAS20/21; maximum permissible repetitive peak forward current for pulse operation as a function of the duty factor.

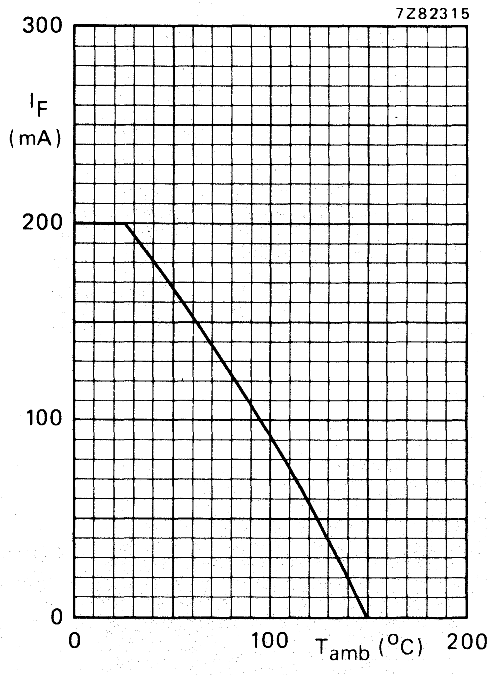


Fig. 8.

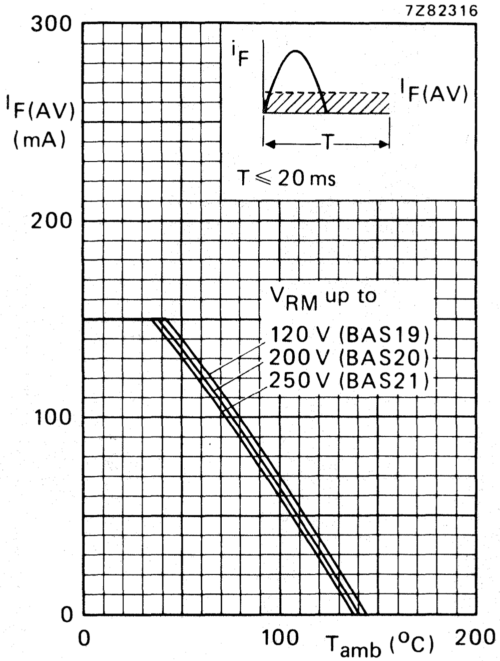


Fig. 9.

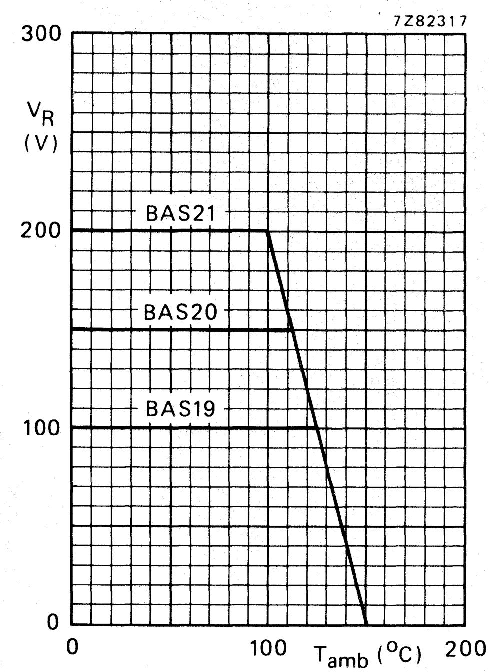


Fig. 10.

Fig. 8 Maximum permissible continuous forward current as a function of the ambient temperature.

Fig. 9 Maximum permissible average rectified forward current as a function of the ambient temperature.

Fig. 10 Maximum permissible continuous reverse voltage as a function of the ambient temperature.

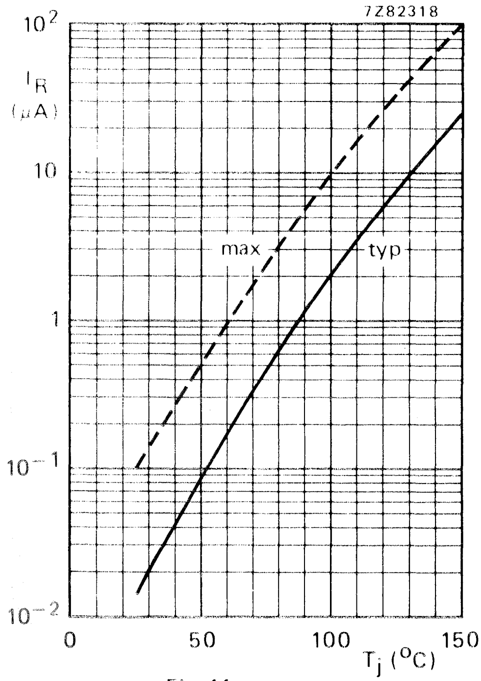


Fig. 11.

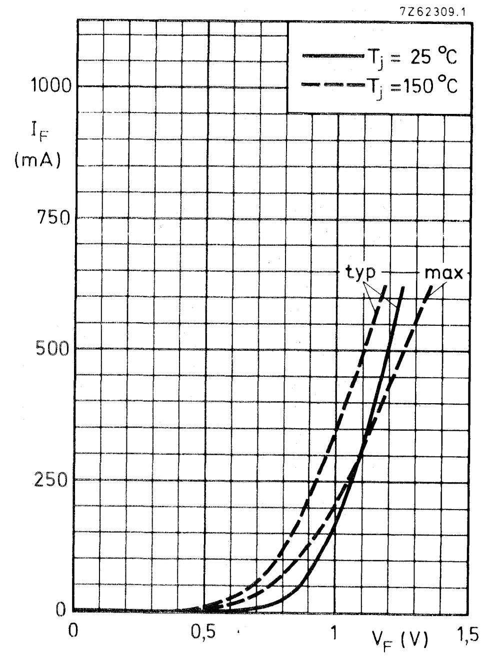


Fig. 12.

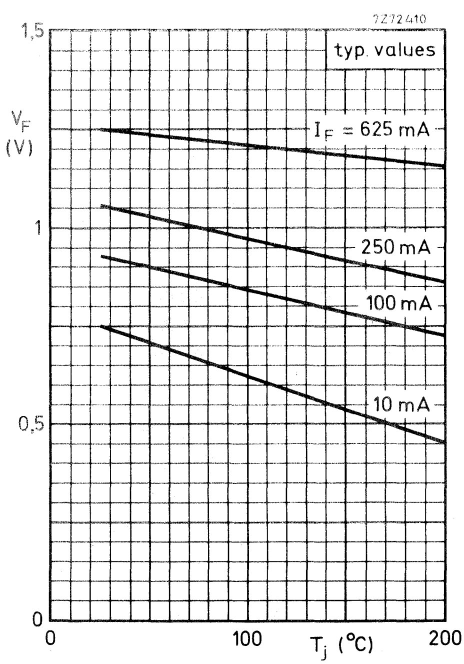


Fig. 13.

Fig. 11 Continuous reverse current as a function of the junction temperature.

Fig. 12 Forward current as a function of forward voltage.

Fig. 13 Forward voltage as a function of the junction temperature.

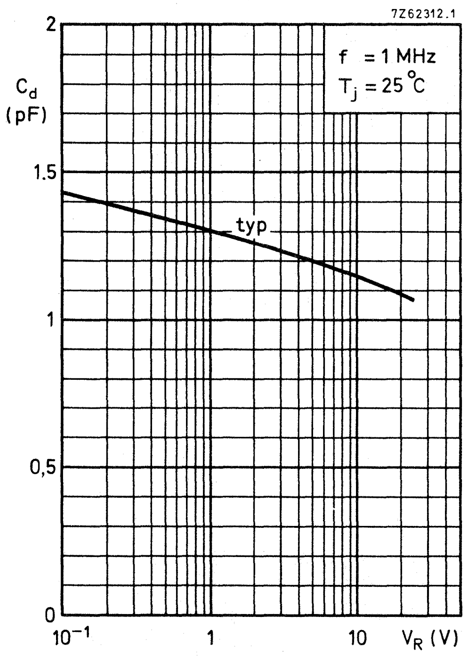

7Z62312.1
f = 1 MHz
T_j = 25 °C
C_d
(pF)
2
1.5
1
0,5
0
typ
10^{-1}
1
10
V_R (V)

Fig. 14.

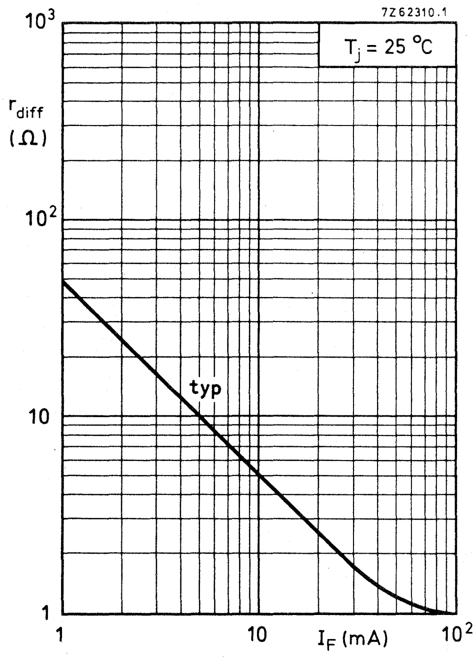

7Z62310.1
T_j = 25 °C
r_{diff}
(Ω)
10^3
10^2
10
1
typ
1
10
I_F (mA)
10^2

Fig. 15.

SILICON PLANAR EPITAXIAL HIGH-SPEED DIODE

The BAS28 consists of two separate diodes in one microminiature envelope intended for surface mounting.

It concerns fast-switching general-purpose diodes.

QUICK REFERENCE DATA

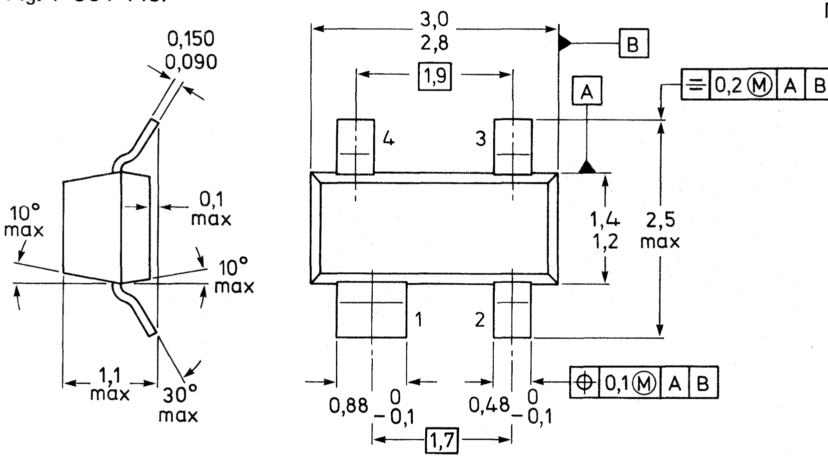
Continuous reverse voltage	V_R	max.	75 V
Repetitive peak reverse voltage	V_{RRM}	max.	85 V
Repetitive peak forward current	I_{FRM}	max.	250 mA
Junction temperature	T_j	max.	175 ^oC
Forward voltage at I_F = 50 mA	V_F	<	1,0 V
Reverse recovery time when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω, measured at I_R = 1 mA	t_{rr}	<	6 ns
Recovery charge when switched from I_F = 10 mA to V_R = 5 V; R_L = 500 Ω	Q_s	<	45 pC

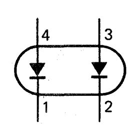
MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-143.

Marking code. A61





7Z85014.6

TOP VIEW

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	75 V
Repetitive peak reverse voltage	V_{RRM}	max.	85 V
Average rectified forward current▲ (averaged over any 20 ms period) up to T_{amb} = 25 °C**	$I_{F(AV)}$	max.	250 mA
Forward current (d.c.)	I_F	max.	250 mA
Repetitive peak forward current	I_{FRM}	max.	250 mA
→ Non-repetitive peak forward current (per crystal)			
t = 1 μs	I_{FSM}	max.	2 A
t = 1 ms	I_{FSM}	max.	1 A
t = 1 s	I_{FSM}	max.	0,5 A
Storage temperature range	T_{stg}		−65 to + 175 °C
Junction temperature	T_j	max.	175 °C

THERMAL RESISTANCE*

From junction to ambient	$R_{th\ j\text{-}a}$	=	430 K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltage			
I_F = 1 mA	V_F	<	715 mV
I_F = 10 mA	V_F	<	855 mV
I_F = 50 mA	V_F	<	1000 mV
I_F = 150 mA	V_F	<	1250 mV
Reverse current			
V_R = 25 V; T_j = 150 °C	I_R	<	30 μA
V_R = 75 V	I_R	<	1 μA
V_R = 75 V; T_j = 150 °C	I_R	<	50 μA
Diode capacitance V_R = 0; f = 1 MHz	C_d	<	2 pF
Forward recovery voltage (see also Fig. 2) when switched to I_F = 10 mA; t_p = 20 ns	V_{fr}	<	1,75 V
Reverse recovery time (see also Fig. 3) when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<	6 ns
Recovery charge (see also Fig. 4) when switched from I_F = 10 mA to V_R = 5 V; R_L = 500 Ω	Q_s	<	45 pC

▲ Measured under pulse conditions. $t_p \leq$ 0,5 ms. $I_{F(AF)}$ = 150 mA, $t_{(av)} \leq$ 1 ms, for sinusoidal operation.

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

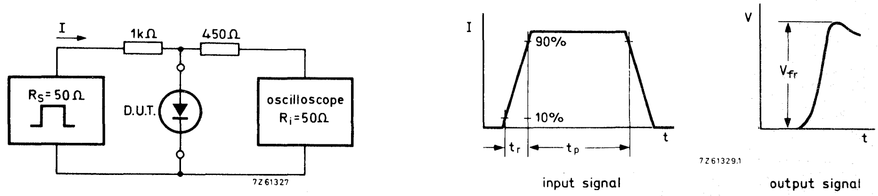


Fig. 2 Forward recovery voltage test circuit and waveforms.

Input signal: forward pulse rise time = t_r = 20 ns; forward current pulse duration t_p = 120 ns; duty factor = δ = 0,01.
Oscilloscope: rise time = t_r = 0,35 ns.
Circuit capacitance C ⩽ 1 pF (C = oscilloscope input capacitance + parasitic capacitance).

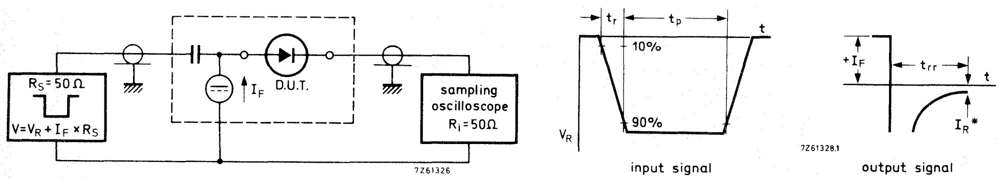


Fig. 3 Reverse recovery time test circuit and waveforms.

Input signal: reverse pulse rise time = t_r = 0,6 ns; reverse pulse duration = t_p = 100 ns; duty factor = δ = 0,05. * t_{rr} up to I_R = 1 mA.
Oscilloscope: rise time = t_r = 0,35 ns.
Circuit capacitance C ⩽ 1 pF (C = oscilloscope input capacitance + parasitic capacitance).

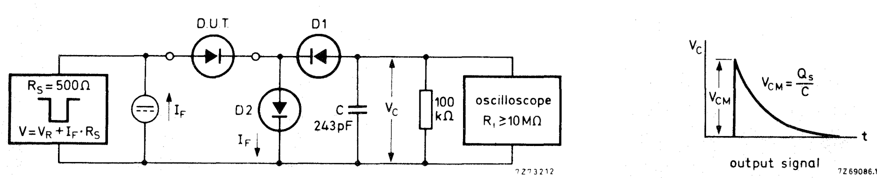


Fig. 4 Recovery charge test circuit and waveform.

D1 = BAW62; D2 = diode with minority carrier life time at 10 mA: < 200 ps

Input signal

Rise time of the reverse pulse	t_r	=	2	ns
Reverse pulse duration	t_p	=	400	ns
Duty factor	δ	=	0,02	

Circuit capacitance C ⩽ 7 pF (C = oscilloscope input capacitance + parasitic capacitance).

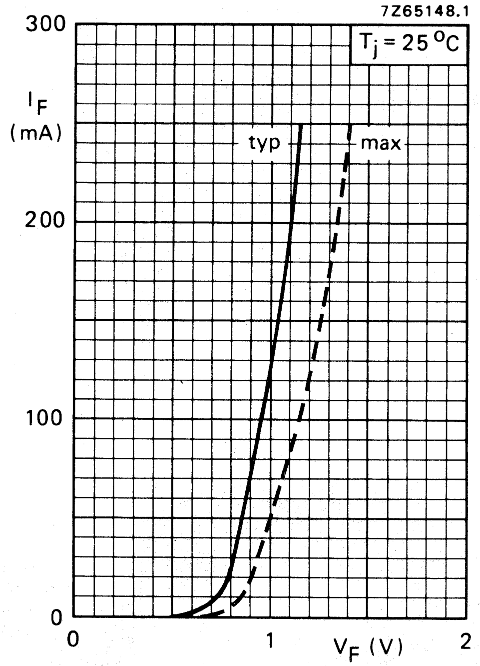


Fig. 5.

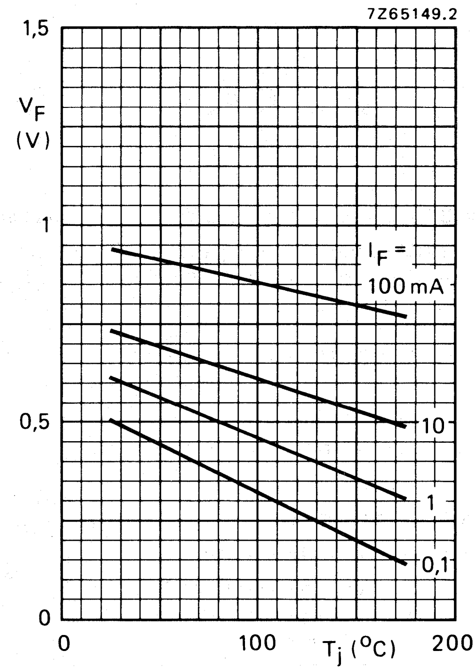


Fig. 6 Typical values.

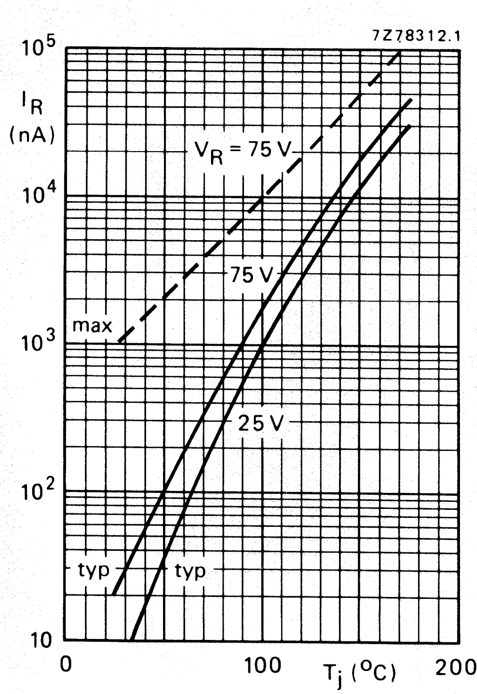


Fig. 7.

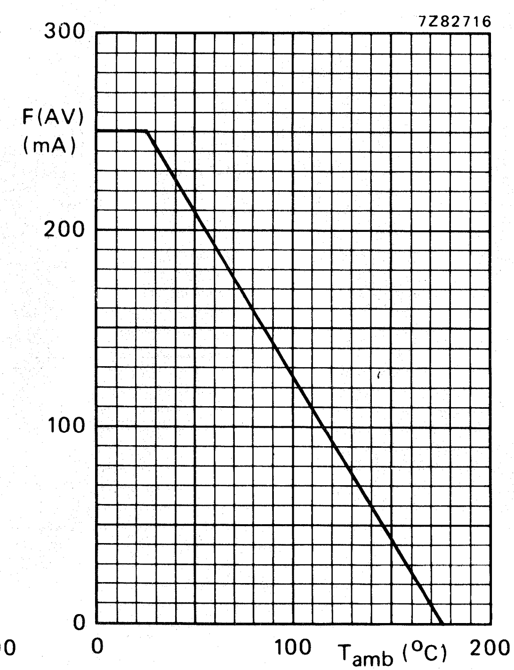


Fig. 8 Current derating curve.

SILICON PLANAR EPITAXIAL HIGH-SPEED DIODES

The BAS29, BAS31 and the BAS35 are silicon planar epitaxial diodes encapsulated in a SOT-23 envelope.

The BAS29 consists of a single diode. The BAS31 has two diodes in series and the BAS35 has two diodes with a common anode. All diodes are designed for switching inductive loads in semi-electronic telephone exchanges.

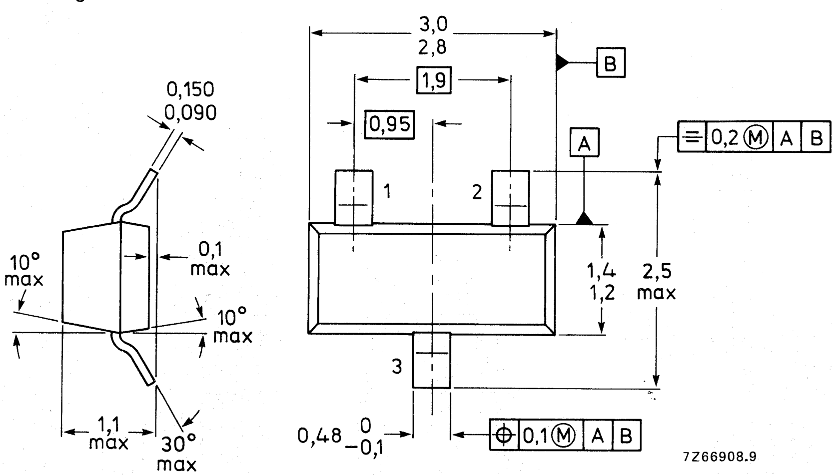
QUICK REFERENCE DATA (per diode)

Continuous reverse voltage	V_R	max.	90	V
Repetitive peak forward current	I_{FRM}	max.	600	mA
Forward current	I_F	max.	250	mA
Junction temperature	T_j	max.	150	^oC
Forward voltage at I_F = 50 mA	V_F	<	0,84	V
Reverse recovery time when switched from I_F = 30 mA to I_R = 30 mA; R_L = 100 Ω; measured at I_R = 3 mA	t_{rr}	<	50	ns

MECHANICAL DATA

Fig. 1 SOT-23.

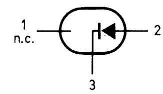
Dimensions in mm



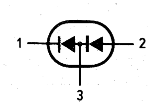
TOP VIEW

Marking code:

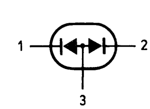
BAS29 = L20
BAS31 = L21
BAS35 = L22



BAS29



BAS31



BAS35

RATINGS (per diode)

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	90	V
Repetitive peak forward current	I_{FRM}	max.	600	mA
Repetitive peak reverse current	I_{RRM}	max.	600	mA
Average rectified forward current (averaged over any 20 ms period)	I_F	max.	250	mA
Non-repetitive peak forward current t = 1 µs; T_j = 25 °C prior to surge; per crystal t = 1 s; T_j = 25 °C prior to surge; per crystal	I_{FSM}	max.	 3 0,75	 A A
Forward current (d.c.)	I_F	max.	250	mA
Repetitive peak reverse energy tp ⩽ 50 s; f ⩽ 20 Hz; T_j = 25 °C	E_{RRM}	⩽	5,0	mJ
Storage temperature	T_{stg}		−65 to +175	°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE

From junction to ambient when mounted on ceramic substrate of 7 mm x 5 mm x 0,5 mm	$R_{th\ j\text{-}a}$	=	430	K/W

CHARACTERISTICS (per diode)

T_j = 25 °C unless otherwise specified

Forward voltage				
I_F = 10 mA	V_F	⩽	0,75	V
I_F = 50 mA	V_F	⩽	0,84	V
I_F = 100 mA	V_F	⩽	0,90	V
I_F = 200 mA	V_F	⩽	1,00	V
I_F = 400 mA	V_F	⩽	1,25	V
Reverse current V_R = 90 V V_R = 90 V; T_j = 150 °C	I_R	 ⩽ ⩽	 100 100	 nA µA
Reverse avalanche breakdown voltage I_R = 1 mA A	$V_{(BR)R}$		120 to 175	V
Diode capacitance V_R = 0; f = 1 MHz	C_d	⩽	35	pF
Reverse recovery time when switched from I_F = 30 mA to I_R = 30 mA; R_L = 100 Ω; measured at I_R = 3 mA	t_{rr}	⩽	50	ns

HIGH-SPEED SILICON DIODE FOR SURFACE MOUNTING

The BAS32 is a planar epitaxial high-speed diode designed for fast logic applications.

This SM diode is a leadless diode in a hermetically sealed SOD-80 envelope with tin-plated metal discs at each end. It is suitable for ''automatic placement'' and as such it can withstand immersion soldering.

The diodes are delivered in ''super 8'' tape.

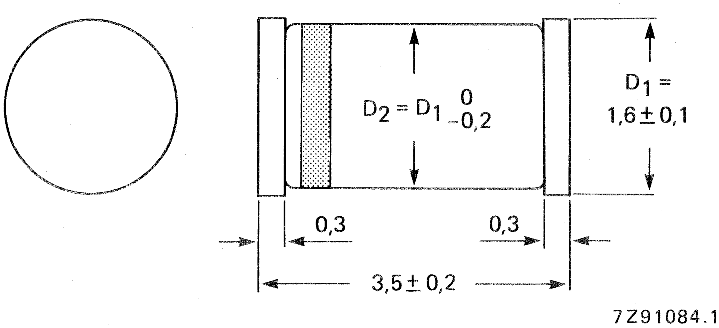
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	75	V
Repetitive peak reverse voltage	V_{RRM}	max.	75	V
Repetitive peak forward current	I_{FRM}	max.	450	mA
Junction temperature	T_j	max.	200	°C
Forward voltage I_F = 100 mA	V_F	<	1	V
Reverse recovery time when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<	4	ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-80.



Cathode indicated by black band.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	75	V
Repetitive peak reverse voltage	V_{RRM}	max.	75	V*
Average rectified forward current	$I_{F(AV)}$	max.	150	mA**
Forward current (d.c.)	I_F	max.	200	mA
Repetitive peak forward current	I_{FRM}	max.	450	mA
Non-repetitive peak forward current				
t = 1 μs	I_{FSM}	max.	2000	mA
t = 1 s	I_{FSM}	max.	500	mA
Storage temperature	T_{stg}	−65 to + 200		°C
Junction temperature	T_j	max.	200	°C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j\text{-}a}$	=	0,6	K/mW

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltages				
I_F = 5 mA	V_F	0,62 to	0,75	V
I_F = 100 mA	V_F	<	1,00	V
I_F = 100 mA; T_j = 100 °C	V_F	<	0,93	V
Reverse currents				
V_R = 20 V	I_R	<	25	nA
V_R = 20 V; T_j = 150 °C	I_R	<	50	μA
V_R = 75 V	I_R	<	5	μA
V_R = 75 V; T_j = 150 °C	I_R	<	100	μA
Diode capacitance				
V_R = 0; f = 1 MHz	C_d	<	2	pF
Forward recovery voltage when switched to				
I_F = 50 mA; t_r = 20 ns	V_{fr}	<	2,5	V

* Measured at zero life time at I_R = 100 μA; V_R > 100 V.

** For sinusoidal operation see Fig. 6. For pulse operation see Figs 4 and 5.

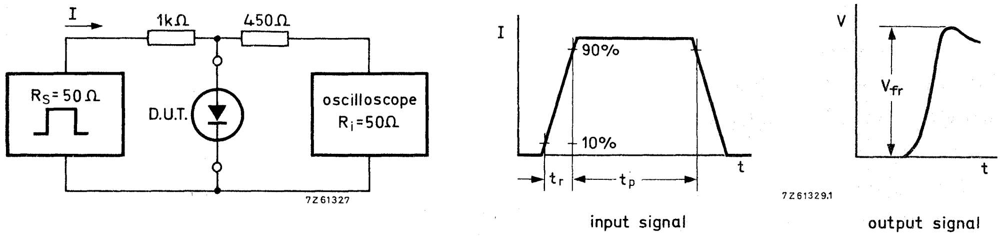


Fig. 2 Forward recovery voltage test circuit and waveforms.

Input signal : Rise time of the forward pulse t_r = 20 ns
Forward current pulse duration t_p = 120 ns
Duty factor δ = 0,01

Oscilloscope: Rise time t_r = 0,35 ns

Circuit capacitance C ⩽ 1 pF (C = oscilloscope input capacitance + parasitic capacitance)

Reverse recovery time when switched from
I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω;
measured at I_R = 1 mA t_{rr} < 4 ns

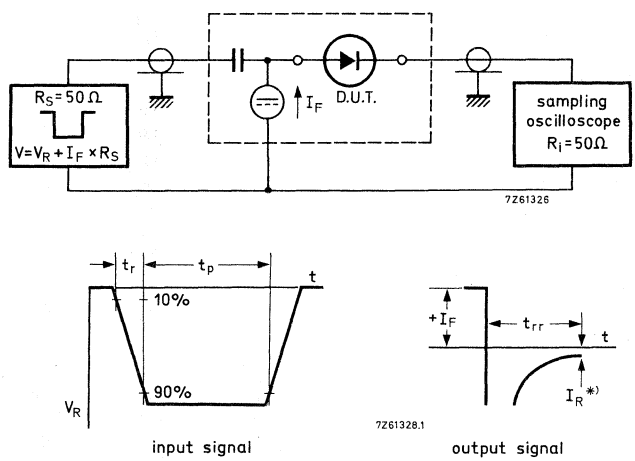


Fig. 3 Reverse recovery time test circuit and waveforms.

Input signal : Rise time of the reverse pulse t_r = 0,6 ns * I_R = 1 mA
Reverse pulse duration t_p = 100 ns
Duty factor δ = 0,05

Oscilloscope: Rise time t_r = 0,35 ns

Circuit capacitance C ⩽ 1 pF (C = oscilloscope input capacitance + parasitic capacitance)

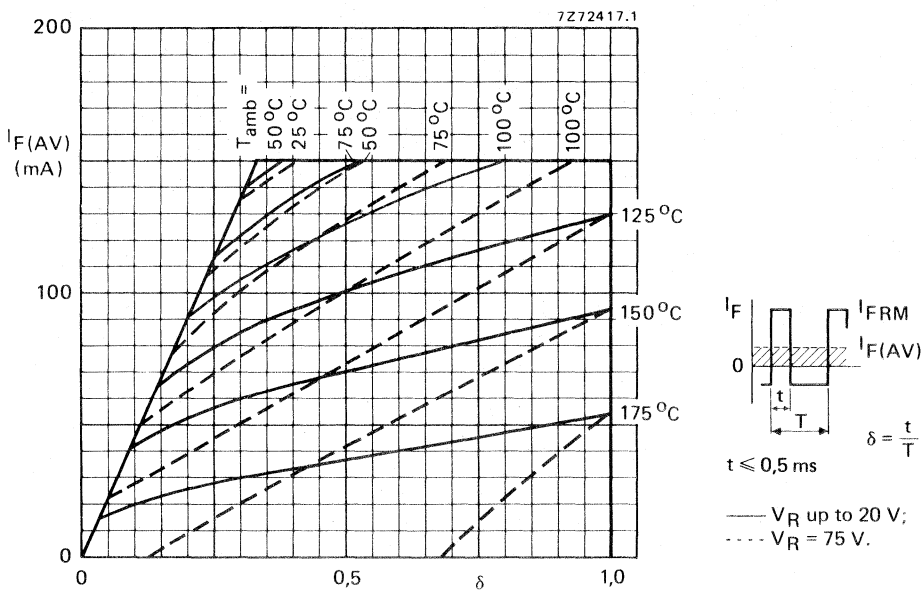


Fig. 4 Maximum permissible average rectified forward current versus duty factor (pulse operated).

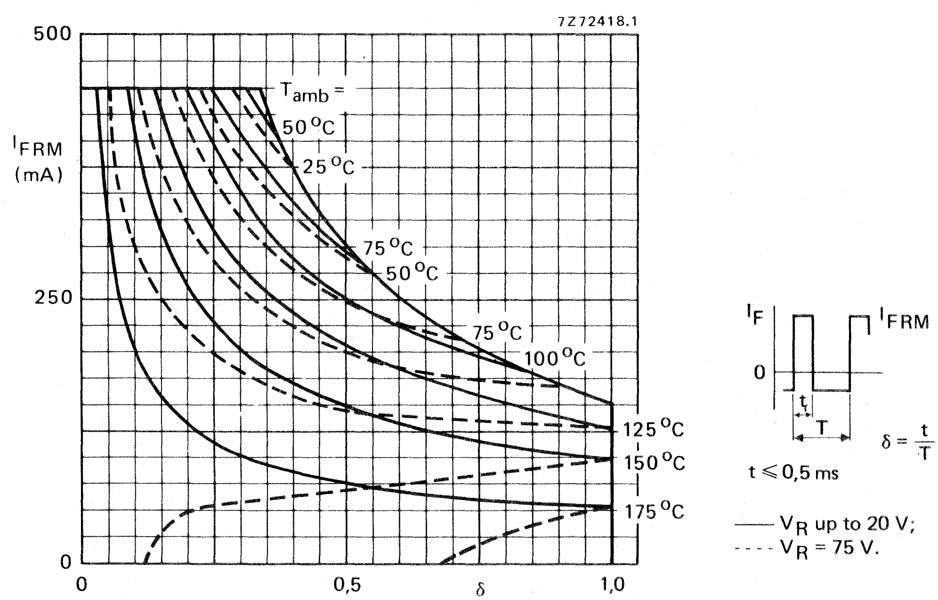


Fig. 5 Maximum permissible repetitive peak forward current versus duty factor (pulse operated).

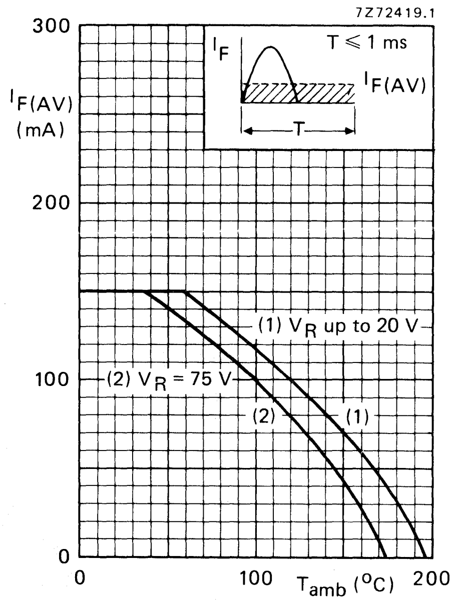


Fig. 6 Maximum permissible average rectified forward current versus ambient temperature.

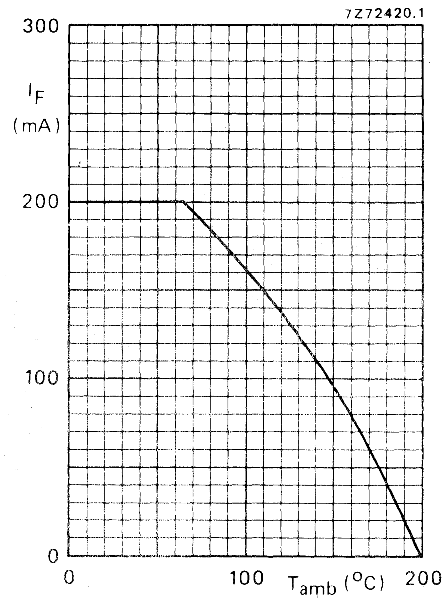


Fig. 7 Maximum permissible continuous forward current versus ambient temperature.

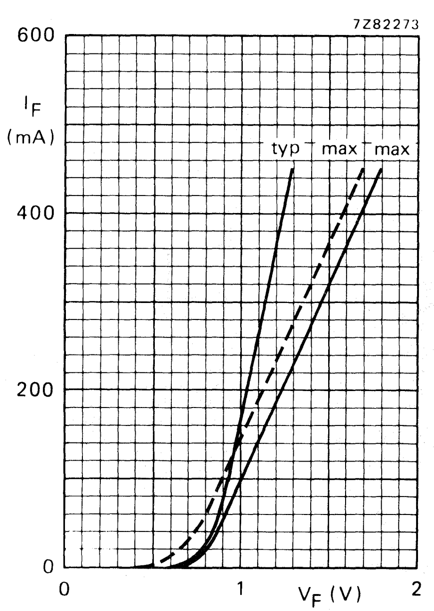


Fig. 8 Forward current versus forward voltage; —— T_j = 25 °C; – – – T_j = 175 °C.

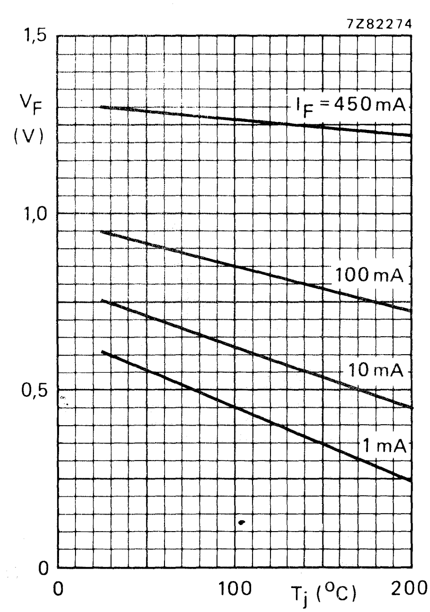


Fig. 9 Forward voltage versus junction temperature; typical values.

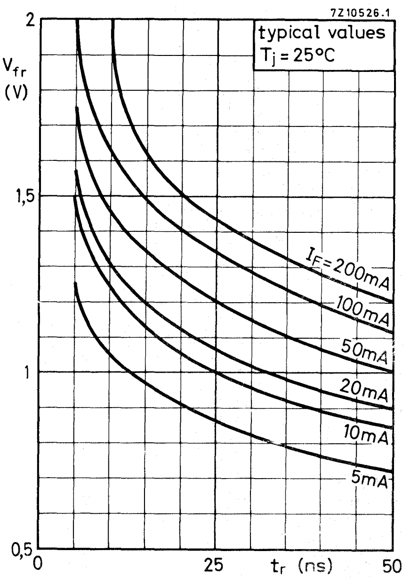


Fig. 10 Forward recovery voltage versus rise time.

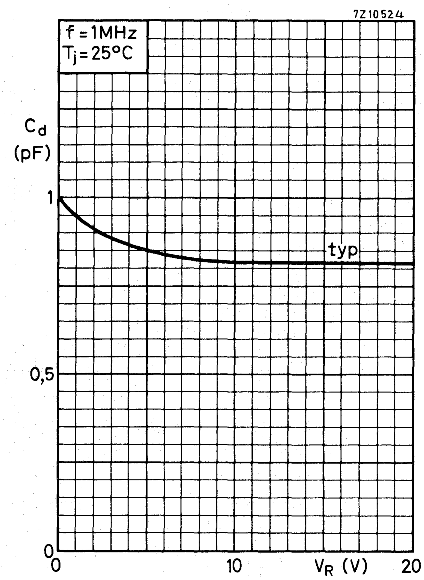


Fig. 11 Diode capacitance versus reverse voltage.

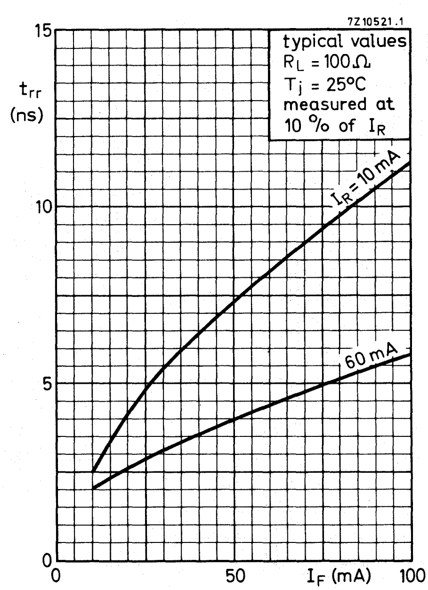


Fig. 12 Reverse recovery time versus forward current.

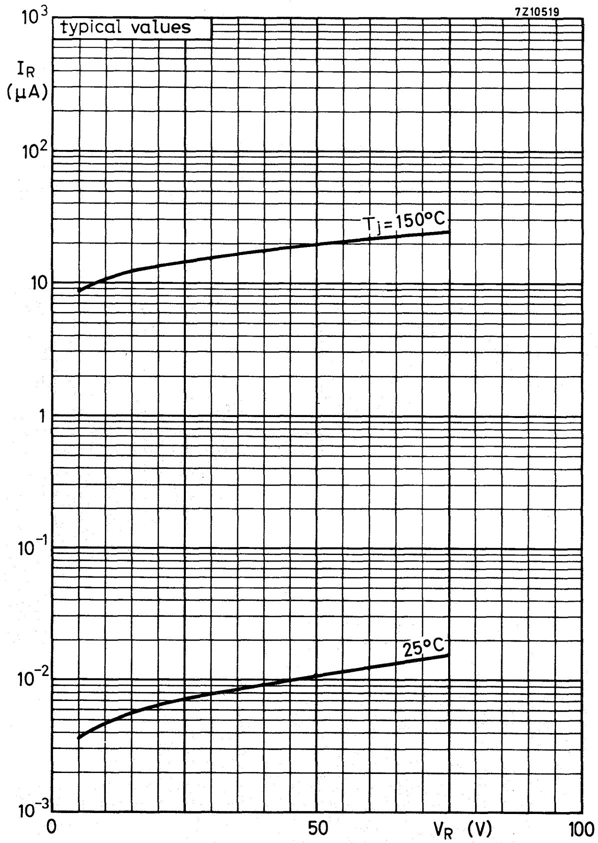


Fig. 13 Reverse current versus reverse voltage.

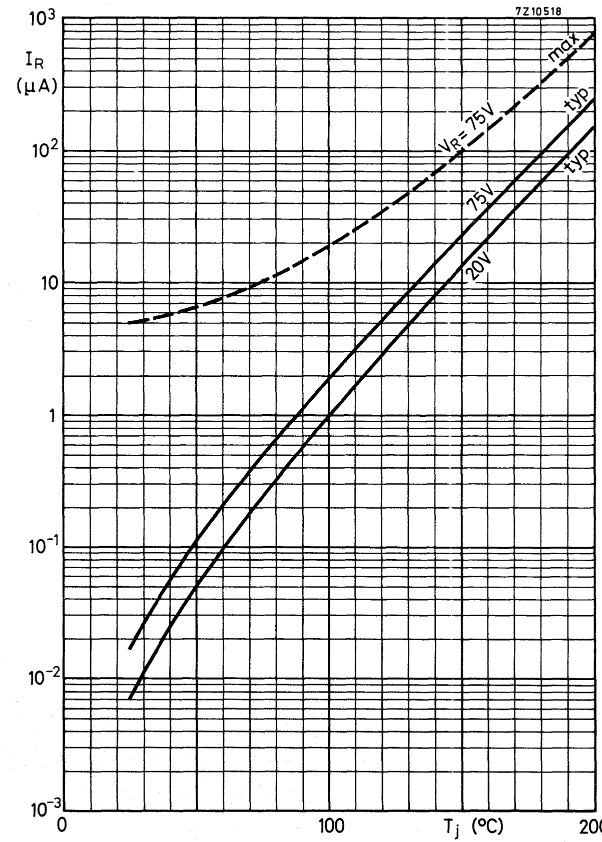


Fig. 14 Reverse current versus junction temperature.

SILICON PLANAR EPITAXIAL ULTRA-HIGH SPEED DIODE

The BAS56 consists of two separate planar epitaxial ultra-high speed, high conductance diodes in one microminiature plastic envelope intended for surface mounting.

The device is primarily intended for core gating in very fast memories using the Surface Mounted Devices (SMD) technology.

QUICK REFERENCE DATA

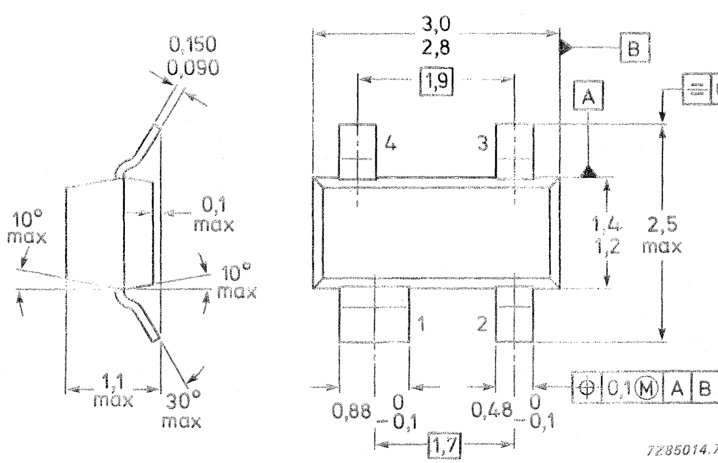
			single diode	series connection	
Continuous reverse voltage	V_R	max.	60	120	V
Repetitive peak reverse voltage	V_{RRM}	max.	60	120	V
Forward current	I_F	max.	200	150	mA
Repetitive peak forward current	I_{FRM}	max.	600	430	mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300		mW
Reverse recovery time when switched from I_F = 400 mA to I_R = 400 mA; R_L = 100 Ω; measured at I_R = 40 mA	t_{rr}	<	6		ns

MECHANICAL DATA

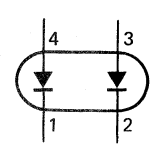
Dimensions in mm

Fig. 1 SOT-143.

Marking code: L51



TOP VIEW



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			single diode	series connection	
Continuous reverse voltage	V_R	max.	60	120	V
Repetitive peak reverse voltage*	V_{RRM}	max.	60	120	V
Forward current	I_F	max.	200	150	mA
Repetitive peak forward current	I_{FRM}	max.	600	430	mA
→ Non-repetitive peak forward current (per crystal)					
t = 1 μs	I_{FSM}	max.	2000		mA
t = 1 s	I_{FSM}	max.	500		mA
Total power dissipation** up to T_{amb} = 25 °C	P_{tot}	max.	300		mW
Storage temperature range	T_{stg}		−65 to +150		°C
Junction temperature	T_j	max.	150		°C

THERMAL RESISTANCE

From junction to ambient**	$R_{th\ j\text{-}a}$	=	430	K/W

CHARACTERISTICS, per diode

T_j = 25 °C unless otherwise specified

Forward voltage				
I_F = 10 mA	V_F	<	0,75	V
I_F = 200 mA	V_F	<	1,00	V
I_F = 200 mA; T_j = 100 °C	V_F	<	0,95	V
I_F = 500 mA	V_F	<	1,25	V
Reverse current				
V_R = 60 V	I_R	<	100	nA
V_R = 60 V; T_j = 150 °C	I_R	<	100	μA
Diode capacitance				
V_R = 0; f = 1 MHz	C_d	<	2,5	pF

* Measured at zero life time at I_R = 10 μA; V_R = 75 V.
** Mounted on a ceramic substrate of 10 mm x 8 mm x 0,6 mm.

Forward recovery voltage when switched to

I_F = 400 mA; t_r1 = 30 ns	V_{fr}	<	120	V
I_F = 400 mA; t_r2 = 100 ns		<	1,5	V

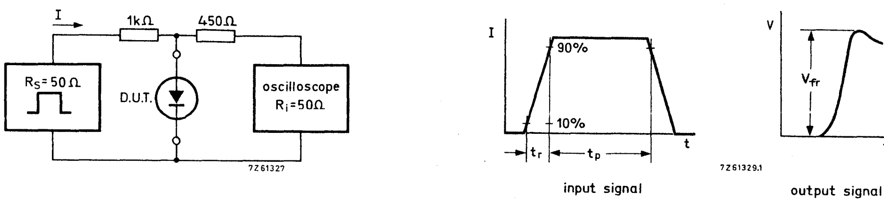


Fig. 2 Test circuit and waveforms; forward recovery voltage.

Input signal:	1st rise time of the forward pulse	t_r1	=	30	ns
	2nd rise time of the forward pulse	t_r2	=	100	ns
	Forward current pulse duration	t_p	=	300	ns
	Duty factor	δ	=	0,01	
Oscilloscope:	Rise time	t_r	=	0,35	ns
	Input capacitance	C_i	$\leqslant$	1	pF

Circuit capacitance C $\leqslant$ 20 pF (C = C_i + parasitic capacitance)

Reverse recovery time when switched from I_F = 400 mA to I_R = 400 mA; R_L = 100 Ω; measured at I_R = 40 mA	t_{rr}	<	6	ns

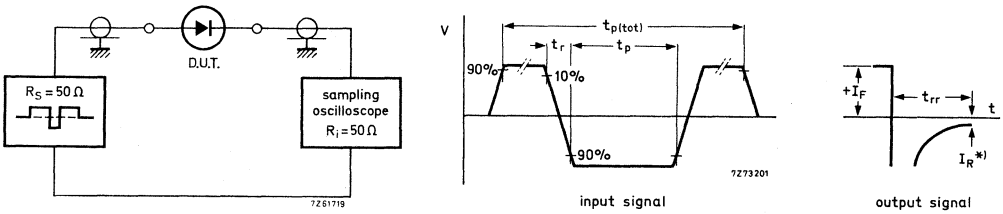


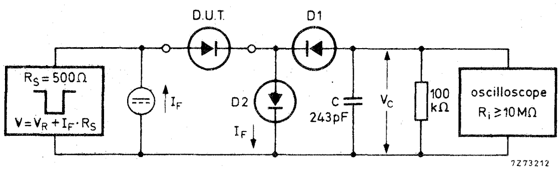
Fig. 3 Test circuits and waveforms; reverse recovery time.

*I_R = 40 mA

Input signal:	Total pulse duration	$t_{p(tot)}$	=	0,2	μs
	Duty factor	δ	=	0,0025	
	Rise time of the reverse pulse	t_r	=	0,6	ns
	Reverse pulse duration	t_p	=	30	ns
Oscilloscope:	Rise time	t_r	=	0,35	ns

Circuit capacitance C $\leqslant$ 1 pF (C = oscilloscope input capacitance + parasitic capacitance)

Recovery charge when switched from I_F = 10 mA to V_R = 5 V; R_L = 500 Ω	Q_s	<	50	pC



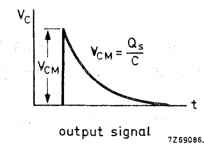


Fig. 4 Test circuit and waveform; recovery charge.

D1 = BAW62

D2 = diode with minority carrier life time at 10 mA			<	200	ps
Input signal:	Rise time of the reverse pulse	t_r	=	2	ns
	Reverse pulse duration	t_p	=	400	ns
	Duty factor	δ	=	0,02	

Circuit capacitance C ⩽ 7 pF (C = oscilloscope input capacitance + parasitic capacitance)

SCHOTTKY BARRIER DIODE

Silicon epitaxial diode in a microminiature plastic envelope. Intended for u.h.f. mixer and fast switching applications in thick and thin-film circuits.

QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	4	V
Forward current (d.c.)	I_F	max.	30	mA
Junction temperature	T_j	max.	100	°C
Forward voltage at I_F = 10 mA	V_F	<	600	mV
Diode capacitance at V_R = 0; f = 1 MHz	C_d	<	1,0	pF
Noise figure at f = 900 MHz	F	<	8,0	dB

MECHANICAL DATA

Dimensions in mm

Marking code

BAT17 = A3

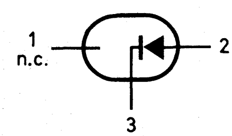
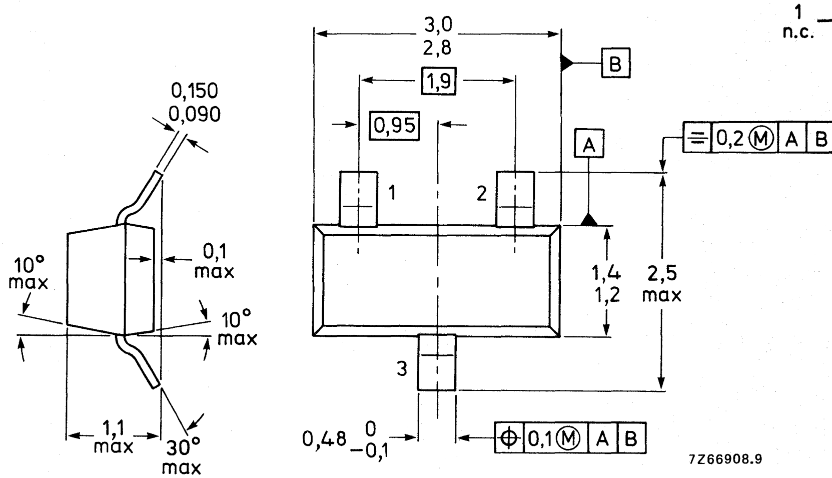


Fig.1 SOT-23.



TOP VIEW

See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	4	V
Forward current (d.c.)**	I_F	max.	30	mA
Storage temperature	T_{stg}	–65 to +100		°C
Junction temperature	T_j	max.	100	°C

THERMAL RESISTANCE*

From junction to ambient**	$R_{th\ j\text{-}a}$	=	430	K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Reverse current				
V_R = 3 V	I_R	$<$	0,25	μA
V_R = 3 V; T_{amb} = 60 °C	I_R	$<$	1,25	μA
Reverse breakdown voltage				
I_R = 10 μA	$V_{(BR)R}$	$>$	4	V
Forward voltage				
I_F = 0,1 mA	V_F	$<$	350	mV
I_F = 1,0 mA	V_F	$<$	450	mV
I_F = 10 mA	V_F	$<$	600	mV
Diode capacitance				
V_R = 0; f = 1 MHz	C_d	$<$	1,0	pF
Noise figure at f = 900 MHz▲	F	$<$	8,0	dB
Series resistance at f = 1 kHz				
I_F = 5 mA	r_D	$<$	15	Ω

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

▲ The local oscillator is adjusted for a diode current of 2 mA. I.F. amplifier noise F_{if} = 1,5 dB; f = 35 MHz.

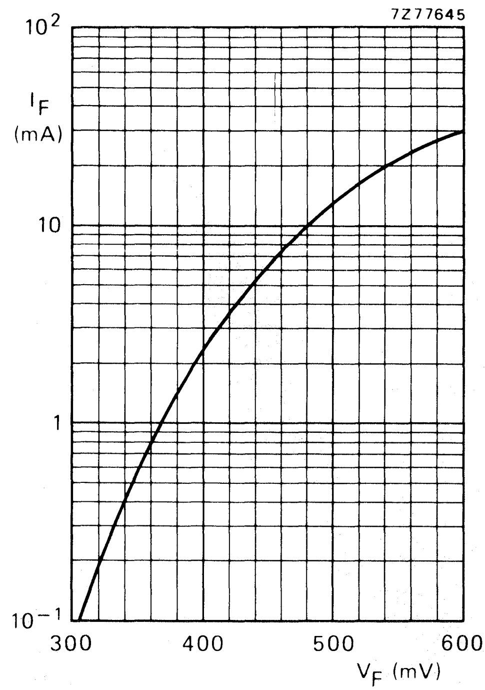


Fig. 2 Typical values.

SILICON PLANAR DIODE

Band switching diode in a microminiature plastic envelope. Intended for thick and thin-film circuits.

QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	35 V
Forward current (d.c.)	I_F	max.	100 mA
Junction temperature	T_j	max.	100 °C
Diode capacitance at f = 1 MHz V_R = 20 V	C_d	typ. <	0,8 pF 1,0 pF
Series resistance at f = 200 MHz I_F = 5 mA	r_D	typ. <	0,5 Ω 0,7 Ω

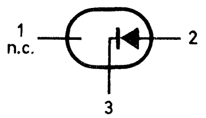
MECHANICAL DATA

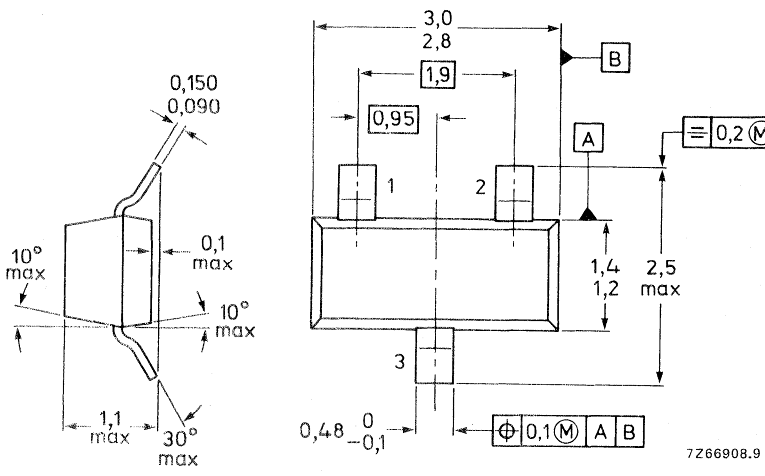
Dimensions in mm

Fig. 1 SOT-23.

Marking code

BAT18 = A2





TOP VIEW

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	35	V
Forward current (d.c.)	I_F	max.	100	mA
Storage temperature	T_{stg}	−55 to + 125		^oC
Junction temperature	T_j	max.	125	^oC

THERMAL RESISTANCE*

From junction to ambient**	$R_{th\ j\text{-}a}$	=	430	K/W

CHARACTERISTICS

T_j = 25 ^oC unless otherwise specified

Forward voltage at I_F = 100 mA	V_F	<	1,2	V
Reverse current				
V_R = 20 V	I_R	<	100	nA
V_R = 20 V; T_j = 60 ^oC	I_R	<	1	μA
Diode capacitance at f = 1 MHz				
V_R = 20 V	C_d	typ.	0,8	pF
		<	1,0	pF
Series resistance at f = 200 MHz				
I_F = 5 mA	r_D	typ.	0,5	Ω
		<	0,7	Ω

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

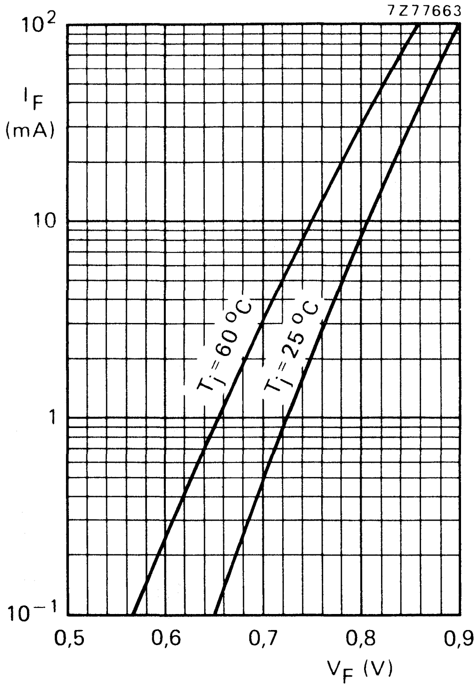


Fig. 2 Typical values.

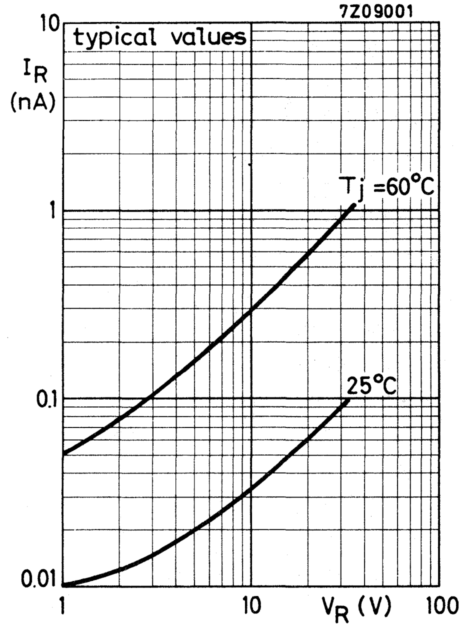


Fig. 3.

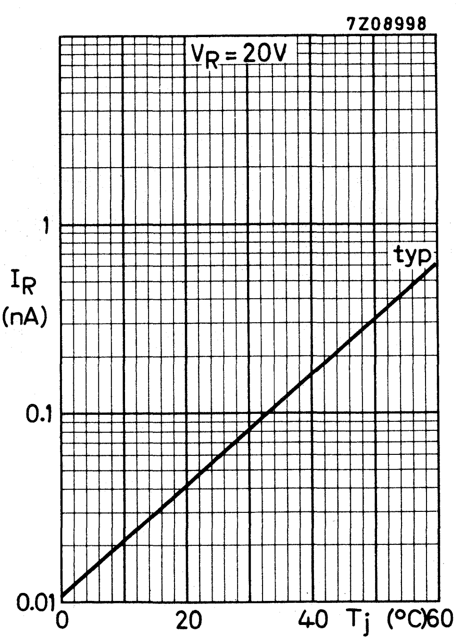


Fig. 4.

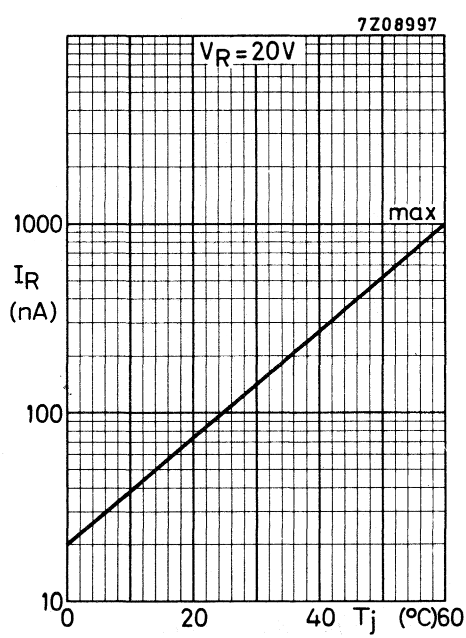


Fig. 5.

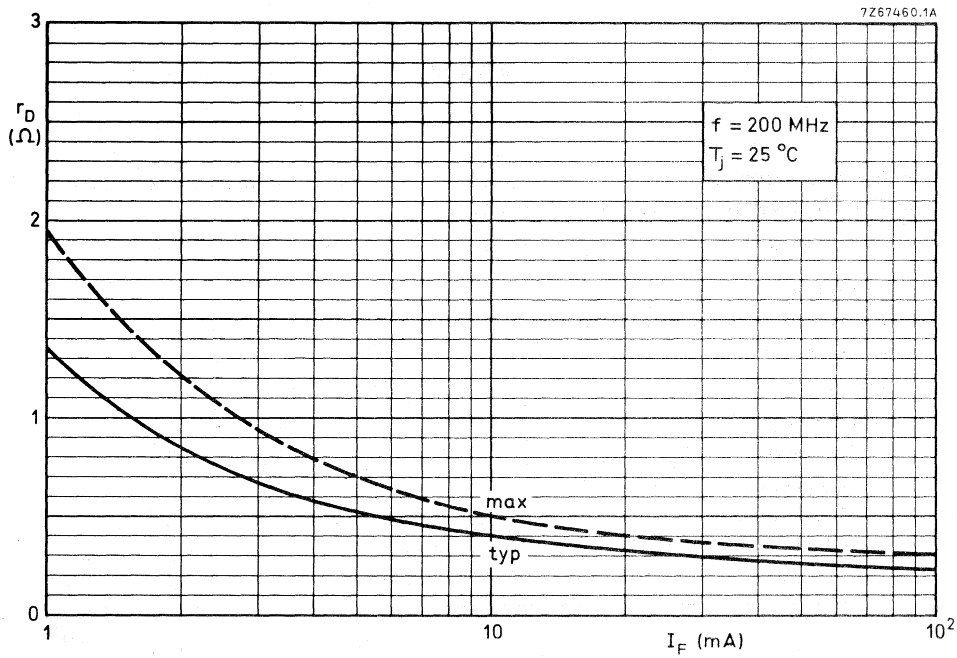


Fig. 6.

SCHOTTKY BARRIER DIODE

Silicon epitaxial Schottky barrier diode with an integrated p-n junction protection ring in a micro-miniature SOT-23 envelope intended for surface mounting.

The diode features especially a low forward voltage.

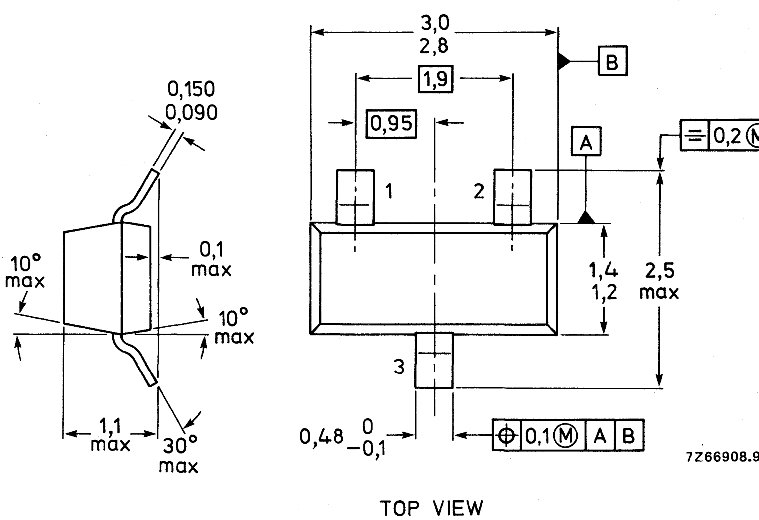
QUICK REFERENCE DATA

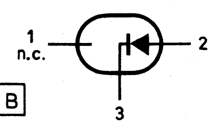
Continuous reverse voltage	V_R	max.	30	V
Forward current (d.c.)	I_F	max.	200	mA
Forward voltage at I_F = 10 mA	V_F	max.	400	mV
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	230	mW
Reverse recovery time when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	≤	5	ns
Junction temperature	T_j	max.	125	°C

Fig. 1 SOT-23

Dimensions in mm

Marking code: L4





RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	30	V
Forward current (d.c.) see Fig. 2	I_F	max.	200	mA
Repetitive peak forward current	I_{FRM}	max.	300	mA
Non-repetitive peak forward current $t < 1$ s	I_{FSM}	max.	600	mA
Total power dissipation up to $T_{amb} = 25$ °C	P_{tot}	max.	230	mW
Storage temperature	T_{stg}		−55 to +150	°C
Junction temperature	T_j	max.	125	°C

THERMAL RESISTANCE

From junction to ambient mounted on a ceramic substrate of 10 mm x 8 mm x 0,6 mm	$R_{th\ j\text{-}a}$	=	430	K/W

CHARACTERISTICS

$T_{amb} = 25$ °C unless otherwise specified

Forward voltage				
$I_F = 0,1$ mA	V_F	⩽	240	mV
$I_F = 1$ mA*	V_F	⩽	320	mV
$I_F = 10$ mA	V_F	⩽	400	mV
$I_F = 30$ mA*	V_F	⩽	500	mV
$I_F = 100$ mA	V_F	=	500	mV
	V_F	<	1000	mV
Reverse current $V_R = 25$ V	I_R	⩽	2	μA
Reverse breakdown voltage	$V_{(BR)R}$	>	30	V
Diode capacitance $V_R = 1$ V; f = 1 MHz	C_d	⩽	10	pF
Reverse recovery time when switched from $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100\ \Omega$; measured at $I_R = 1$ mA	t_{rr}	⩽	5	ns

* Temperature coefficient of forward voltage:
−0,6 %/K at $I_F = 1$ mA
−0,3 %/K at $I_F = 30$ mA

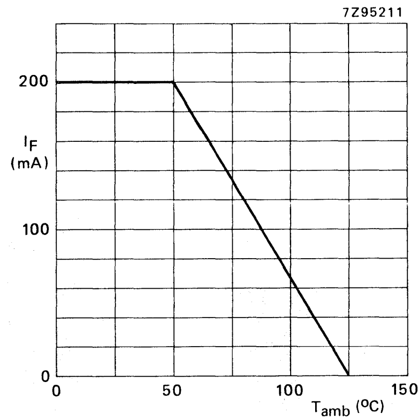


Fig. 2 Derating curve maximum ambient temperature.

DEVELOPMENT DATA

SCHOTTKY BARRIER DIODE

Two separate silicon epitaxial Schottky barrier diodes with an integrated p-n junction protection ring in one microminiature SOT-143 envelope, intended for surface mounting (SMD technology).

The device features a low forward voltage drop.

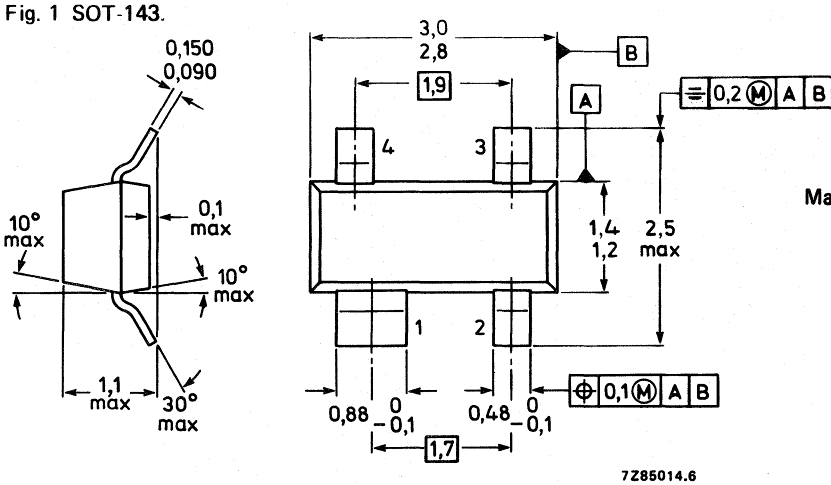
QUICK REFERENCE DATA

			single diode	double-diode operation	
Continuous reverse voltage	V_R	max.	30	30	V
Continuous reverse voltage series connection	V_R	max.	–	60	V
Forward current	I_F	max.	200	110	mA
Repetitive peak forward current	I_{FRM}	max.	300	200	mA
Non-repetitive peak forward current	I_{FSM}	max.	600		mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	230		mW
Reverse recovery time when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	⩽	5		ns

MECHANICAL DATA

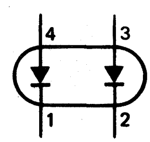
Dimensions in mm

Fig. 1 SOT-143.



TOP VIEW

Marking code : L41



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			single diode	double-diode operation	
Continuous reverse voltage	V_R	max.	30	30	V
Continuous reverse voltage series connection	V_R	max.	–	60	V
Forward current (see Fig. 2)	I_F	max.	200	110*	mA
Repetitive peak forward current	I_{FRM}	max.	300	200	mA
Non-repetitive peak forward current $t < 1$ s	I_{FSM}	max.	600		mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	230		mW
Storage temperature	T_{stg}		–65 to + 150		°C
Junction temperature	T_j	max.	125		°C

THERMAL RESISTANCE

From junction to ambient mounted on a ceramic substrate of 10 mm x 8 mm x 0,6 mm	$R_{th\ j\text{-}a}$	430	K/W

CHARACTERISTICS, per diode

T_{amb} = 25 °C unless otherwise specified

Forward voltage				
I_F = 0,1 mA	V_F	⩽	240	mV
I_F = 1 mA**		⩽	320	mV
I_F = 10 mA	V_F	⩽	400	mV
I_F = 30 mA**		⩽	500	mV
I_F = 100 mA	V_F	=	500	mV
		<	1000	mV
Reverse current V_R = 25 V	I_R	⩽	2	µA
Reverse breakdown voltage	$V_{(BR)R}$	>	30	V
Diode capacitance V_R = 1 V; f = 1 MHz	C_d	⩽	10	pF
Reverse recovery time when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	⩽	5	ns

* If both diodes are in forward operation at the same moment, total device current max. 110 mA. If one diode is in reverse and the other in forward operation at the same moment, total device current max. 200 mA.

** Temperature coefficient of forward voltage: –0,6%/K at I_F = 1 mA.

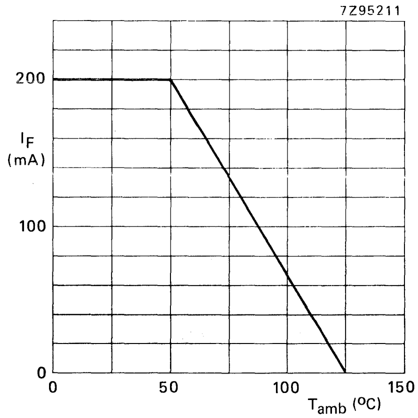


Fig. 2 Derating curve maximum ambient temperature.

DEVELOPMENT DATA

SILICON PLANAR EPITAXIAL HIGH-SPEED DIODE

The BAV23 consists of two separate planar epitaxial high-speed diodes in one microminiature plastic envelope intended for surface mounting.

The device is designed for switching and general applications where high breakdown voltages are required.

QUICK REFERENCE DATA

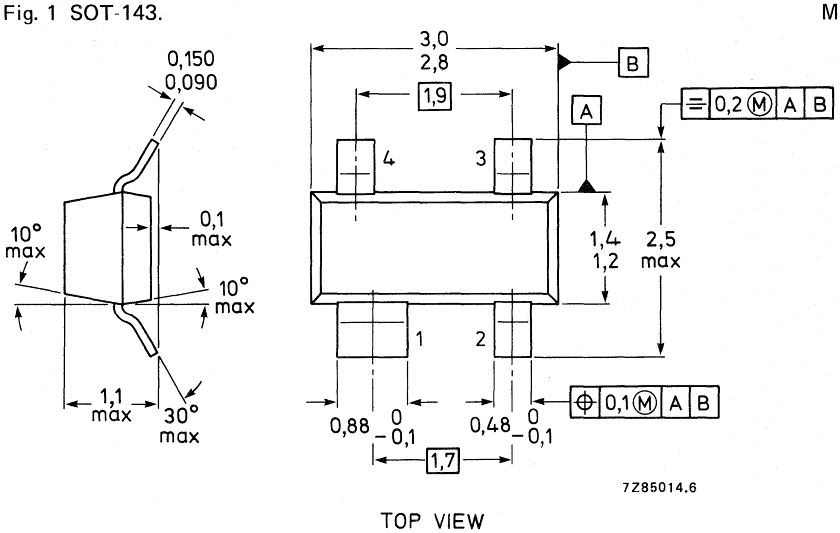
			single diode	series connection	
Continuous reverse voltage	V_R	max.	200	400	V
Repetitive peak reverse voltage	V_{RRM}	max.	250	500	V
Average forward current	$I_{F(AV)}$	max.	200	120	mA
Repetitive peak forward current	I_{FRM}	max.	625	450	mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300		mW
Reverse recovery time when switched from I_F = 30 mA to I_R = 30 mA; R_L = 100 Ω; measured at I_R = 3 mA	t_{rr}	<	50		ns

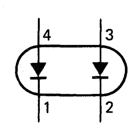
MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-143.

Marking code: L30





RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			single diode	series connection	
Continuous reverse voltage	V_R	max.	200	400	V
Repetitive peak reverse voltage	V_{RRM}	max.	250	500	V
Average forward current	$I_{F(AV)}$	max.	200	120	mA
Repetitive peak forward current	I_{FRM}	max.	625	450	mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300		mW
Storage temperature	T_{stg}		−65 to +150		°C
Junction temperature	T_j	max.	150		°C

THERMAL RESISTANCE

From junction to ambient on a ceramic substrate of 8 mm x 10 mm x 0,6 mm	$R_{th\ j\text{-}a}$	430	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			single diode	series connection	
Forward voltage					
I_F = 100 mA	V_F	<	1000	2000	mV
I_F = 200 mA	V_F	<	1250	2500	mV
Reverse current $V_R = V_{Rmax}$	I_R	<	100	100	nA
Reverse breakdown voltage 1 I_R = 100 µA	$V_{(BR)R}$	>	250	500	V
Differential forward resistance I_F = 10 mA	r_f	typ.	5	10	Ω
Diode capacitance V_R = 0; f = 1 MHz	C_d	<	5	2,5	pF
Reverse recovery time when switched from I_F = 30 mA to I_R = 30 mA; R_L = 100 Ω; measured at I_R = 3 mA	t_{rr}	<	50	50	ns

SILICON PLANAR EPITAXIAL HIGH-SPEED DIODES

The BAV70 consists of two diodes in a microminiature plastic envelope. The cathodes are commoned and the unit is intended for high-speed switching in thick and thin-film circuits.

QUICK REFERENCE DATA (per diode)

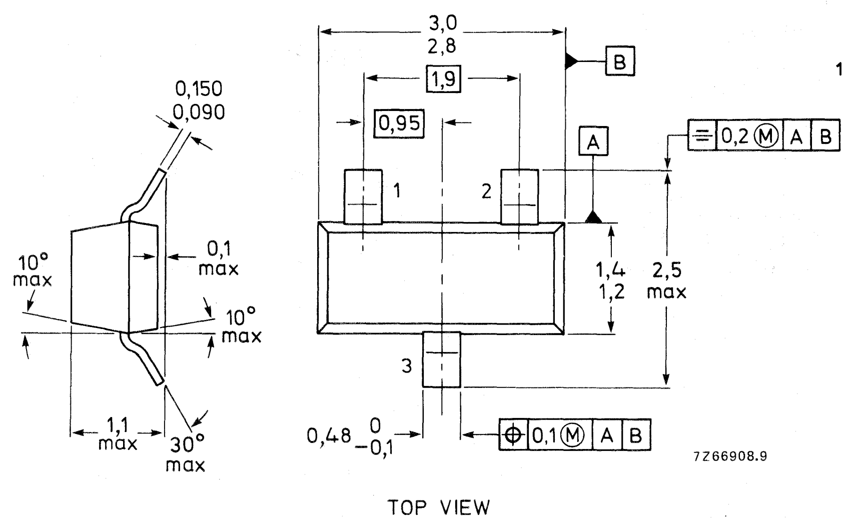
Continuous reverse voltage	V_R	max.	70	V
Repetitive peak reverse voltage	V_{RRM}	max.	70	V
Repetitive peak forward current	I_{FRM}	max.	250	mA
Junction temperature	T_j	max.	175	^oC
Forward voltage at I_F = 50 mA	V_F	<	1,0	V
Reverse recovery time when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<	6	ns
Recovery charge when switched from I_F = 10 mA to V_R = 5 V; R_L = 500 Ω	Q_s	<	45	pC

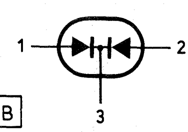
MECHANICAL DATA Dimensions in mm

Fig. 1 SOT-23.

Marking code

BAV70 = A4





See also *Soldering recommendations.*

RATINGS (per diode)

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	70	V
Repetitive peak reverse voltage	V_{RRM}	max.	70	V
Average rectified forward current▲ (averaged over any 20 ms period)	$I_{F(AV)}$	max.	250	mA
Forward current (d.c.)	I_F	max.	250	mA
Repetitive peak forward current	I_{FRM}	max.	250	mA
→ Non-repetitive peak forward current (per crystal)				
t = 1 μs	I_{FSM}	max.	2	A
t = 1 ms	I_{FSM}	max.	1	A
t = 1 s	I_{FSM}	max.	0,5	A
Storage temperature range	T_{stg}		−65 to + 175	°C
Junction temperature	T_j	max.	175	°C

THERMAL RESISTANCE*

From junction to ambient**	$R_{th\ j\text{-}a}$	=	430	K/W

CHARACTERISTICS (per diode)

T_j = 25 °C unless otherwise specified

Forward voltage				
I_F = 1 mA	V_F	<	715	mV
I_F = 10 mA	V_F	<	855	mV
I_F = 50 mA	V_F	<	1000	mV
I_F = 150 mA	V_F	<	1250	mV
Reverse current				
V_R = 25 V; T_j = 150 °C	I_R	<	60	μA
V_R = 70 V	I_R	<	5	μA
V_R = 70 V; T_j = 150 °C	I_R	<	100	μA
Diode capacitance				
V_R = 0; f = 1 MHz	C_d	<	1,5	pF
Forward recovery voltage when switched to				
I_F = 10 mA; t_r = 20 ns	V_{fr}	<	1,75	V

▲ Measured under pulse conditions : pulse time $t_p \leqslant$ 0,5 ms.
For sinusoidal operation $I_{F(AV)}$ = 150 mA; averaging time $t_{(av)} \leqslant$ 1 ms.

* See *Thermal characteristics.*

**Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

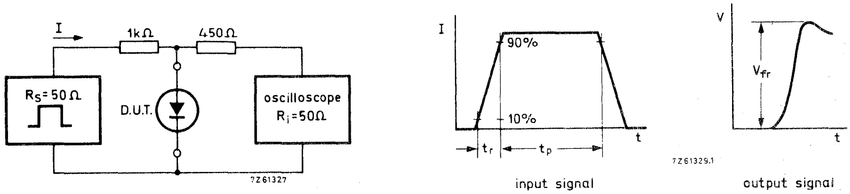


Fig. 2 Test circuit and waveforms; forward recovery voltage.

Input signal : Rise time of the forward pulse t_r = 20 ns; Forward current pulse duration t_p = 120 ns; Duty factor δ = 0,01

Oscilloscope : Rise time t_r = 0,35 ns

Circuit capacitance C $\leqslant$ 1 pF (C = oscilloscope input capacitance + parasitic capacitance)

Reverse recovery time when switched from
I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω;
measured at I_R = 1 mA t_{rr} < 6 ns

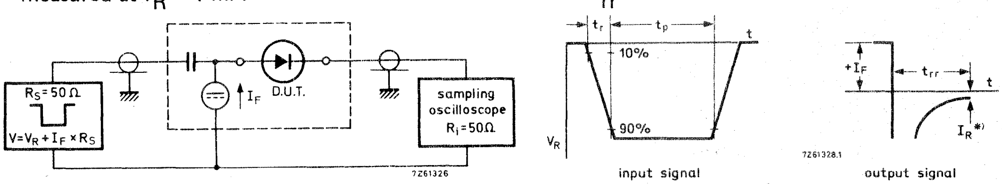


Fig. 3 Test circuit and waveforms; reverse recovery time.

*) I_R = 1 mA

Input signal : Rise time of the reverse pulse t_r = 0,6 ns; reverse pulse duration t_p = 100 ns; duty factor δ = 0,05

Oscilloscope : Rise time t_r = 0,35 ns

Circuit capacitance C $\leqslant$ 1 pF (C = oscilloscope input capacitance + parasitic capacitance)

Recovery charge when switched from
I_F = 10 mA to V_R = 5 V; R_L = 500 Ω Q_s < 45 pC

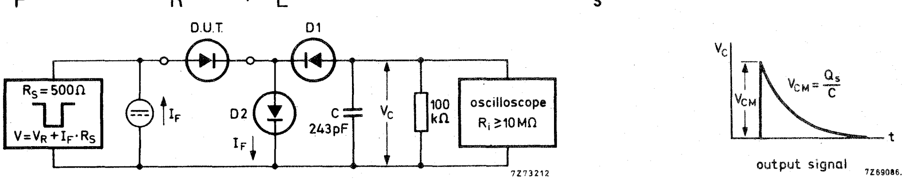


Fig. 4 Test circuit and waveform; recovery charge.

D1 = BAW62

D2 = diode with minority carrier life time at 10 mA: < 200 ps

Input signal : Rise time of the reverse pulse = t_r = 2 ns; Reverse pulse duration = t_p = 400 ns; Duty factor = δ = 0,02

Circuit capacitance C $\leqslant$ 7 pF (C = oscilloscope input capacitance + parasitic capacitance)

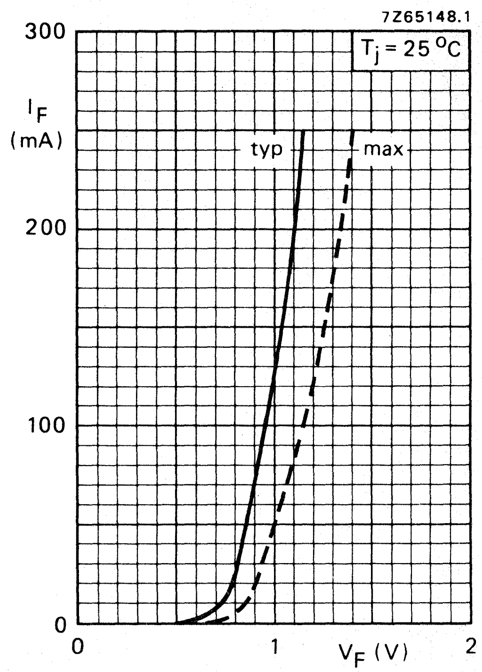


Fig. 5

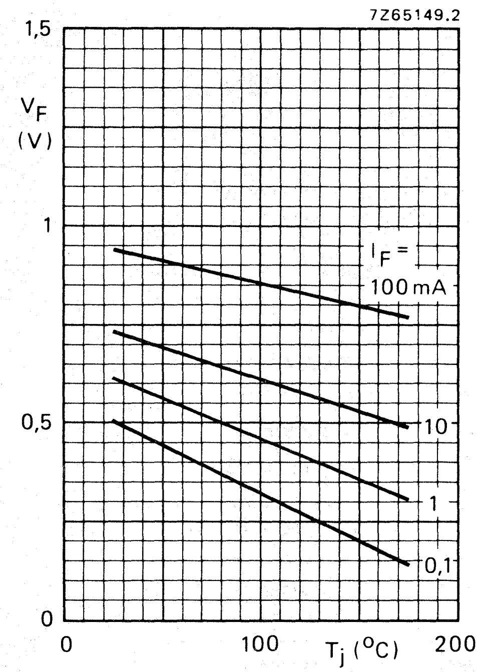


Fig. 6

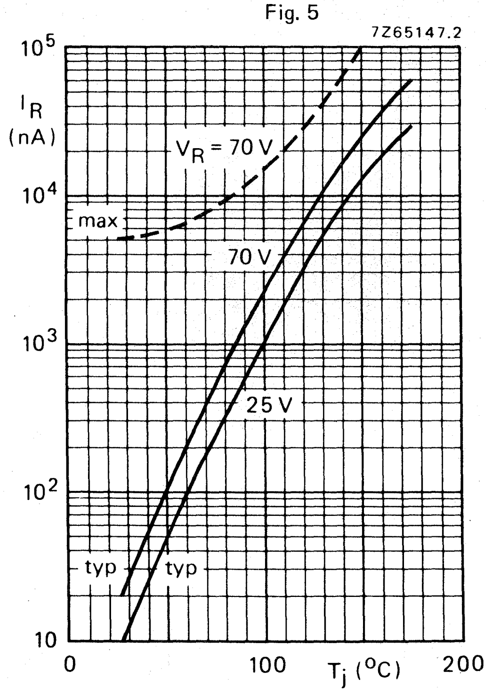


Fig. 7

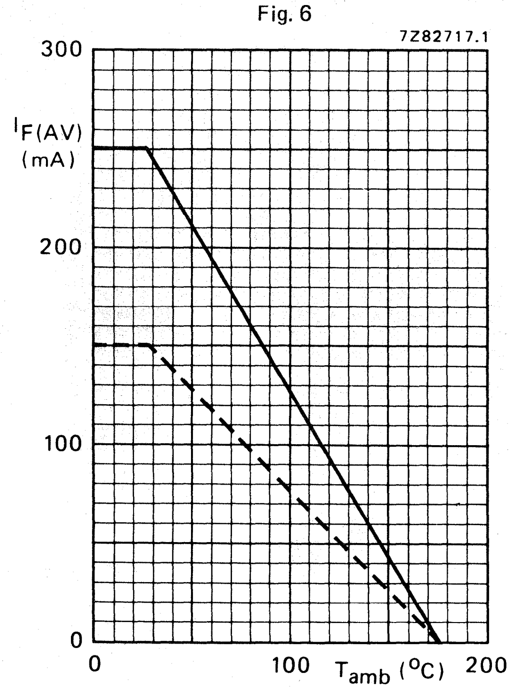


Fig. 8 ——— single diode
– – – – – double diode, equally loaded.

SILICON PLANAR EPITAXIAL HIGH-SPEED DIODES

The BAV99 consists of two diodes in a microminiature plastic envelope. The diodes are connected in series and the unit is intended for high-speed switching in thick and thin-film circuits.

QUICK REFERENCE DATA (per diode)

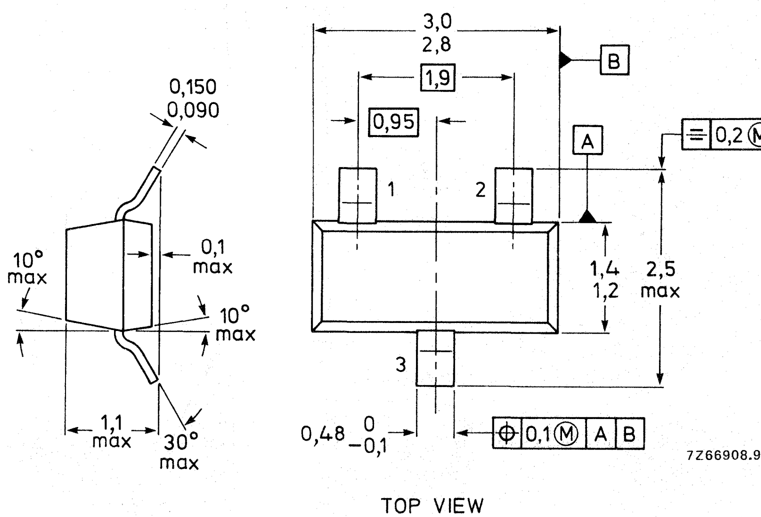
Continuous reverse voltage	V_R	max.	70	V
Repetitive peak reverse voltage	V_{RRM}	max.	70	V
Repetitive peak forward current	I_{FRM}	max.	250	mA
Junction temperature	T_j	max.	175	°C
Forward voltage at I_F = 50 mA	V_F	<	1,0	V
Reverse recovery time when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<	6	ns
Recovery charge when switched from I_F = 10 mA to V_R = 5 V; R_L = 500 Ω	Q_s	<	45	pC

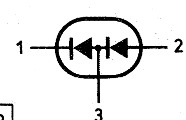
MECHANICAL DATA Dimensions in mm

Fig. 1 SOT-23.

Marking code

BAV99 = A7





See also *Soldering recommendations.*

RATINGS (per diode)

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	70 V
Repetitive peak reverse voltage	V_{RRM}	max.	70 V
Average rectified forward current▲ (averaged over any 20 ms period)	$I_{F(AV)}$	max.	250 mA
Forward current (d.c.)	I_F	max.	250 mA
Repetitive peak forward current	I_{FRM}	max.	250 mA
→ Non-repetitive peak forward current (per crystal)			
t = 1 μs	I_{FRM}	max.	2 A
t = 1 ms	I_{FRM}	max.	1 A
t = 1 s	I_{FRM}	max.	0,5 A
Storage temperature range	T_{stg}		−65 to + 175 °C
Junction temperature	T_j	max.	175 °C

THERMAL RESISTANCE*

From junction to ambient**	$R_{th\,j\text{-}a}$	=	430 K/W

CHARACTERISTICS (per diode)

T_j = 25 °C unless otherwise specified

Forward voltage			
I_F = 1 mA	V_F	<	715 mV
I_F = 10 mA	V_F	<	855 mV
I_F = 50 mA	V_F	<	1000 mV
I_F = 150 mA	V_F	<	1250 mV
Reverse current			
V_R = 25 V; T_j = 150 °C	I_R	<	30 μA
V_R = 70 V	I_R	<	2,5 μA
V_R = 70 V; T_j = 150 °C	I_R	<	50 μA
Diode capacitance			
V_R = 0; f = 1 MHz	C_d	<	1,5 pF
Forward recovery voltage when switched to I_F = 10 mA; t_r = 20 ns	V_{fr}	<	1,75 V

▲ Measured under pulse conditions: pulse time $t_p \leq 0{,}5$ ms.
For sinusoidal operation $I_{F(AV)}$ = 150 mA; averaging time $t_{(av)} \leq 1$ ms.

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

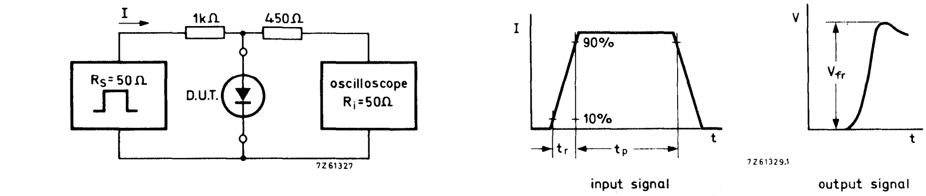


Fig. 2 Test circuit and waveforms; forward recovery voltage.

Input signal: Rise time of the forward pulse t_r = 20 ns;
Forward current pulse duration = t_p = 120 ns. Duty factor = δ = 0,01.
Oscilloscope: Rise time t_r = 0,35 ns.

Circuit capacitance C ⩽ 1 pF (C = oscilloscope input capacitance + parasitic capacitance).

Reverse recovery time when switched from
I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω;
measured at I_R = 1 mA — t_{rr} < 6 ns

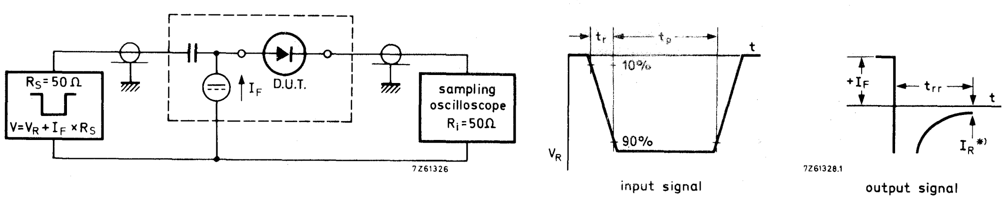


Fig. 3 Test circuit and waveforms; reverse recovery time.

Input signal: Rise time of the reverse pulse t_r = 0,6 ns
Reverse pulse duration t_p = 100 ns. Duty factor δ = 0,05.
Oscilloscope: Rise time t_r = 0,35 ns.

*) I_R = 1 mA

Circuit capacitance C ⩽ 1 pF (C = oscilloscope input capacitance + parasitic capacitance).

Recovery charge when switched from
I_F = 10 mA to V_R = 5 V; R_L = 500 Ω — Q_s < 45 pC

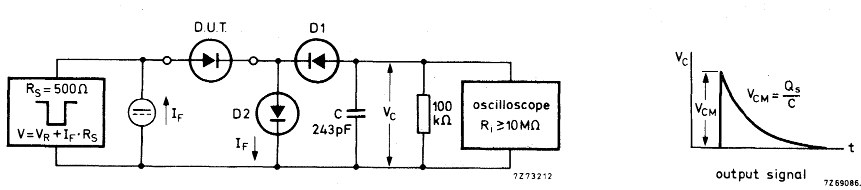


Fig. 4 Test and waveform; recovery charge.

D2 = diode with minority carrier life time at 10 mA: < 200 ps; D1 = BAW62.

Input signal: Rise time of the reverse pulse t_r = 2 ns
Reverse pulse duration t_p = 400 ns. Duty factor δ = 0,02.

Circuit capacitance C ⩽ 7 pF (C = oscilloscope input capacitance + parasitic capacitance).

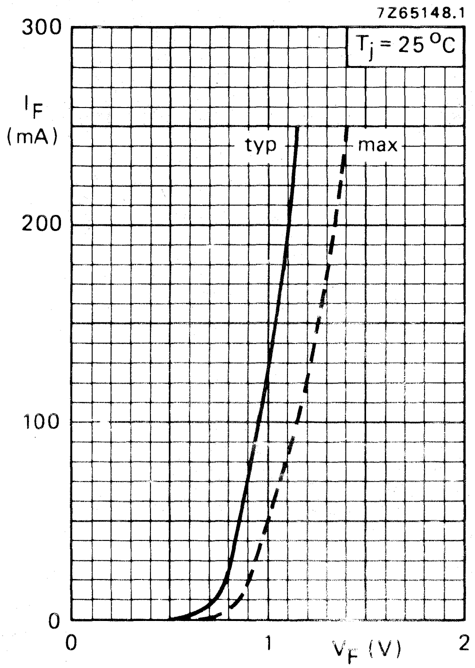


Fig. 5.

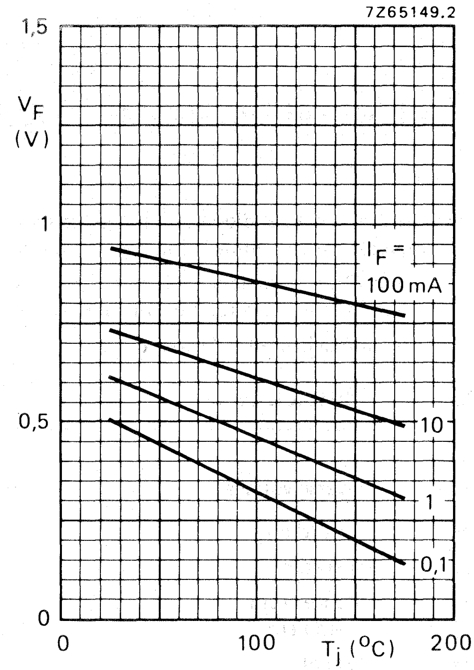


Fig. 6 Typical values.

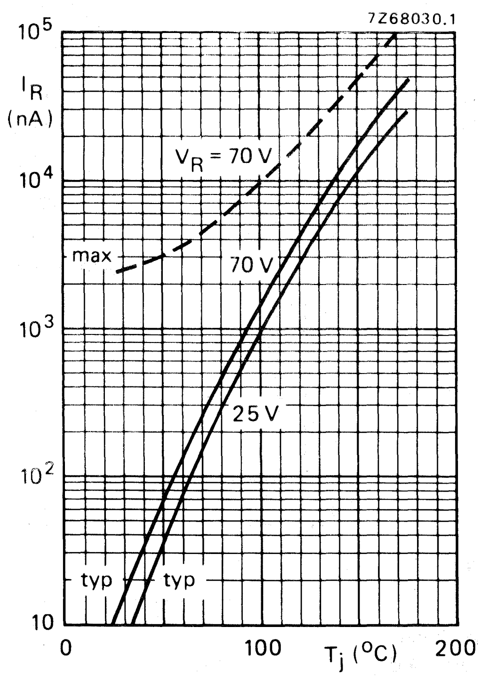


Fig. 7.

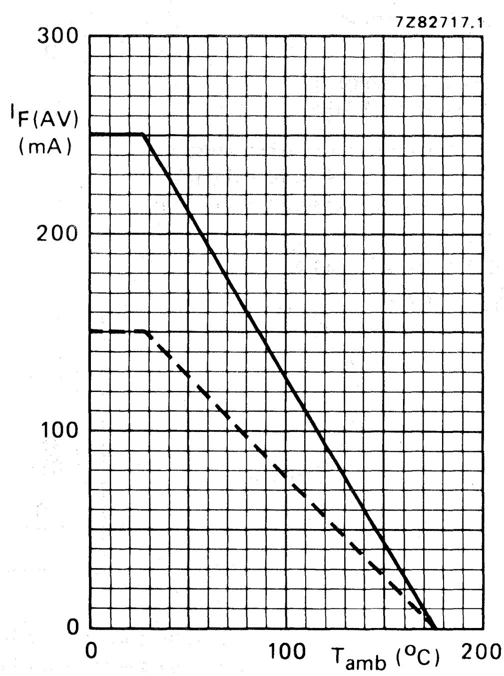


Fig. 8 ——— single diode
– – – – double diode; equally loaded.

GENERAL PURPOSE DIODES FOR SURFACE MOUNTING

Silicon planar epitaxial diodes; intended for switching and general purposes in industrial equipment e.g. oscilloscopes, digital voltmeters and video output stages in colour television.

The SM DIODE is a leadless diode in an hermetically sealed glass envelope with tin plated metal discs at each end. It is suitable for Automatic Placement and as such it can withstand immersion soldering.

The diodes are delivered in "super 8" tape.

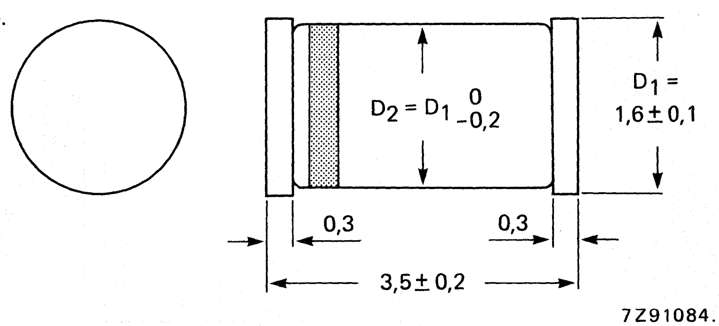
QUICK REFERENCE DATA

			BAV100	BAV101	BAV102	BAV103	
Continuous reverse voltage	V_R	max.	50	100	150	200	V
Forward current (d.c.)	I_F	max.	250				mA
Junction temperature	T_j	max.	175				°C
Thermal resistance from junction to ambient	$R_{th\ j\text{-}a}$	=	0,375				K/mW
Forward voltage at I_F = 100 mA	V_F	<	1,0				V
Reverse current at $V_R = V_{Rmax}$	I_R	<	100				nA
Diode capacitance at V_R = 0; f = 1 MHz	C_d	typ.	1,5				pF
		<	5,0				pF
Reverse recovery time when switched from I_F = 30 mA to I_R = 30 mA; R_L = 100 Ω; measured at I_R = 3 mA	t_{rr}	<	50				ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-80.



The BAV100 cathode is indicated by a green and a black band.
The BAV101 cathode is indicated by a green and a brown band.
The BAV102 cathode is indicated by a green and a red band.
The BAV103 cathode is indicated by a green and an orange band.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BAV100	BAV101	BAV102	BAV103	
Continuous reverse voltage	V_R	max.	50	100	150	200	V
Repetitive peak reverse voltage	V_{RRM}	max.	60	120	200	250	V
Average rectified forward current	$I_{F(AV)}$	max.	250				mA[1]
Forward current (d.c.)	I_F	max.	250				mA
Repetitive peak forward current	I_{FRM}	max.	625				mA
Non-repetitive peak forward current							
$t < 1$ s; $T_j = 25\ ^oC$	I_{FSM}	max.	1				A
$t = 1\ \mu s$; $T_j = 25\ ^oC$	I_{FSM}	max.	5				A
Total power dissipation up to $T_{amb} = 25\ ^oC$	P_{tot}	max.	400				mW
Storage temperature	T_{stg}		−65 to + 175				^oC
Junction temperature	T_j	max.	175				^oC

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j\text{-}a}$	=	0,375	K/mW

CHARACTERISTICS

$T_j = 25\ ^oC$ unless otherwise specified

			BAV100	BAV101	BAV102	BAV103	
Forward voltage							
$I_F = 100$ mA	V_F	<	1,0				V
$I_F = 200$ mA	V_F	<	1,25				V
Reverse breakdown voltage							
$I_R = 100\ \mu A$	$V_{(BR)R}$	>	60	120	200	250	V[2]
Reverse current							
$V_R = V_{Rmax}$	I_R	<	100				nA
$V_R = V_{Rmax}$; $T_j = 150\ ^oC$	I_R	<	100				μA
Differential resistance							
$I_F = 10$ mA	r_{diff}	typ.	5				Ω
Diode capacitance							
$V_R = 0$; f = 1 MHz	C_d	typ.	1,5				pF
		<	5,0				pF
Reverse recovery time when switched from $I_F = 30$ mA to $I_R = 30$ mA; $R_L = 100\ \Omega$; measured at $I_R = 3$ mA	t_{rr}	<	50				ns

[1]) For sinusoidal operation see Figs 7 to 10. For pulse operation see Figs 3 to 6.
[2]) At zero life time, measured under pulse conditions to avoid excessive dissipation and voltage limited at 275 V.

Test circuit and waveforms:

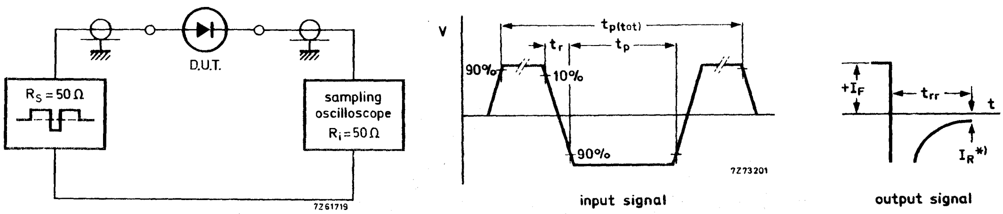


Fig. 2.

*) $I_R = 3$ mA

Input signal:	Total pulse duration	$t_{p(tot)}$	=	2 µs
	Duty factor	δ	=	0,0025
	Rise time of the reverse pulse	t_r	=	0,6 ns
	Reverse pulse duration	t_p	=	100 ns
Oscilloscope:	Rise time	t_r	=	0,35 ns

Circuit capacitance $C \leqslant 1$ pF (C = oscilloscope input capacitance + parasitic capacitance)

DEVELOPMENT DATA

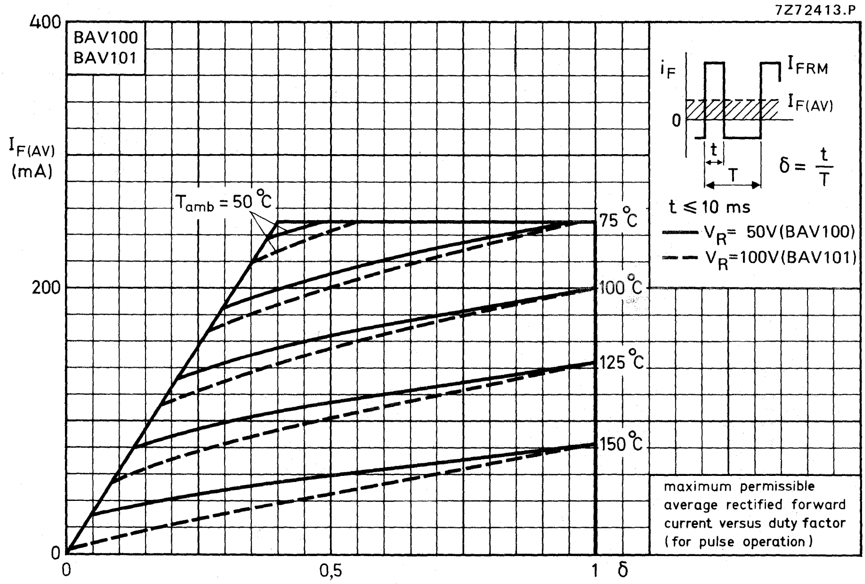

7Z72413.P
BAV100
BAV101
$I_{F(AV)}$ (mA)
400
200
0
T_{amb} = 50 °C
75 °C
100 °C
125 °C
150 °C
0
0,5
1 δ
i_F
I_{FRM}
$I_{F(AV)}$
0
t
T
δ = t/T
t ⩽ 10 ms
V_R = 50V (BAV100)
V_R = 100V (BAV101)
maximum permissible average rectified forward current versus duty factor (for pulse operation)

Fig. 3.

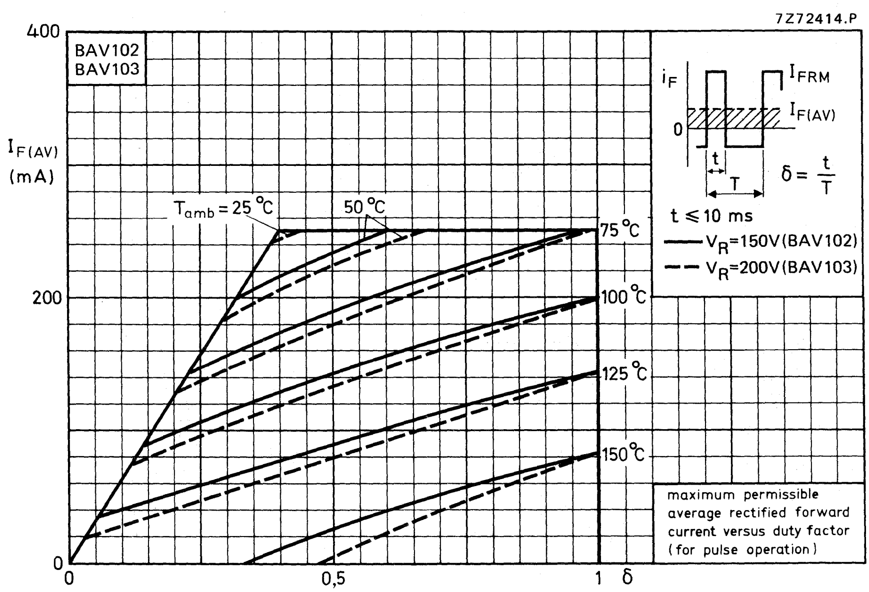

7Z72414.P
BAV102
BAV103
$I_{F(AV)}$ (mA)
400
200
0
T_{amb} = 25 °C
50 °C
75 °C
100 °C
125 °C
150 °C
0
0,5
1 δ
i_F
I_{FRM}
$I_{F(AV)}$
0
t
T
δ = t/T
t ⩽ 10 ms
V_R = 150V (BAV102)
V_R = 200V (BAV103)
maximum permissible average rectified forward current versus duty factor (for pulse operation)

Fig. 4.

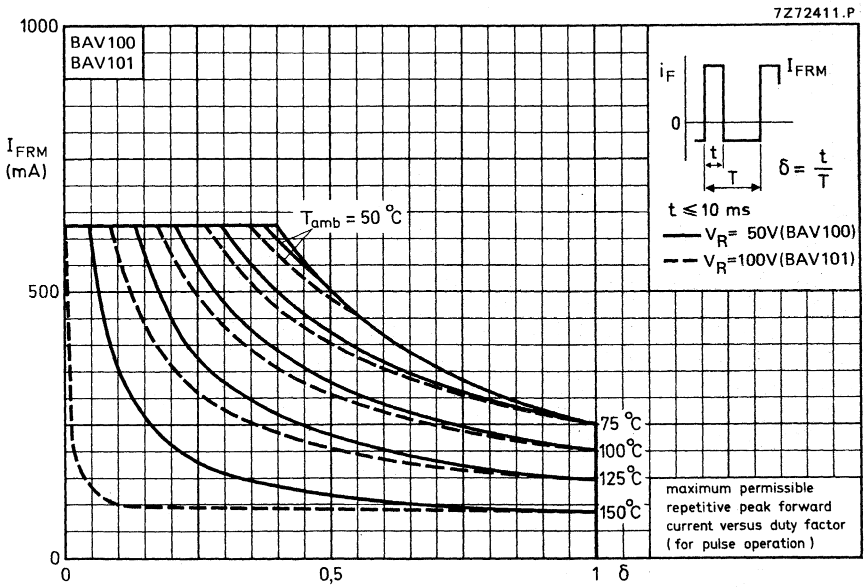

7Z72411.P
1000
BAV100
BAV101
I FRM
(mA)
500
0
0
0,5
1 δ
Tamb = 50 °C
75 °C
100 °C
125 °C
150 °C
iF
IFRM
0
t
T
δ = t/T
t ≤ 10 ms
VR= 50V(BAV100)
VR=100V(BAV101)
maximum permissible
repetitive peak forward
current versus duty factor
(for pulse operation)

Fig. 5.

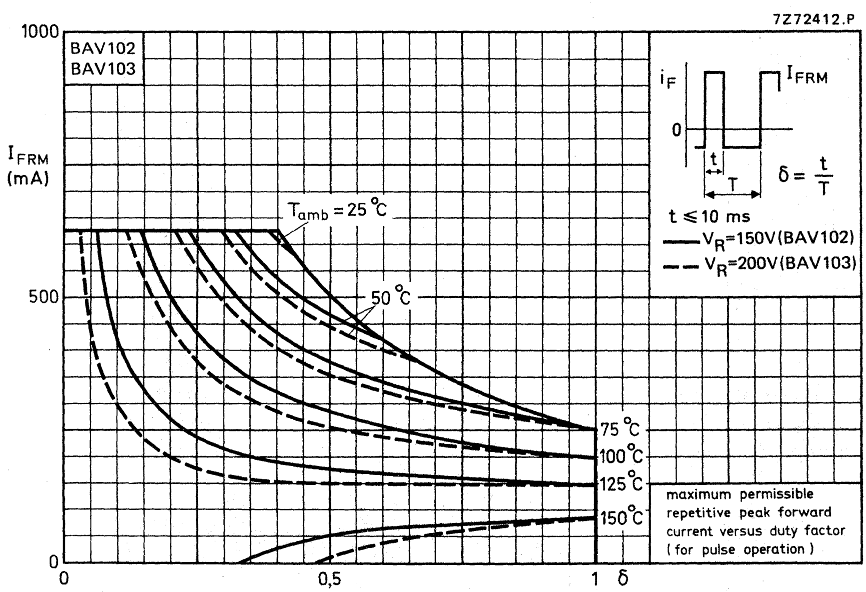

7Z72412.P
1000
BAV102
BAV103
I FRM
(mA)
500
0
0
0,5
1 δ
Tamb = 25 °C
50 °C
75 °C
100 °C
125 °C
150 °C
iF
IFRM
0
t
T
δ = t/T
t ≤ 10 ms
VR=150V(BAV102)
VR=200V(BAV103)
maximum permissible
repetitive peak forward
current versus duty factor
(for pulse operation)

Fig. 6.

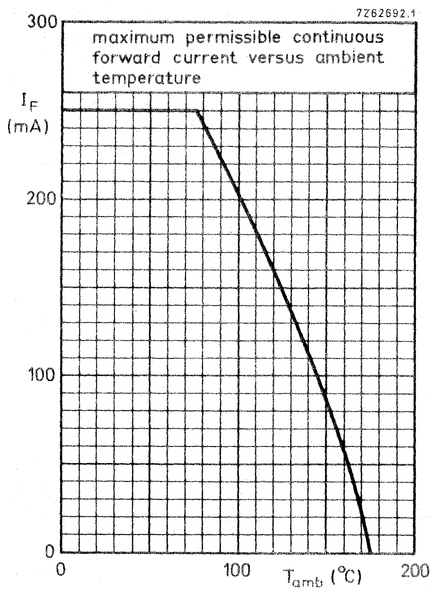


Fig. 7.

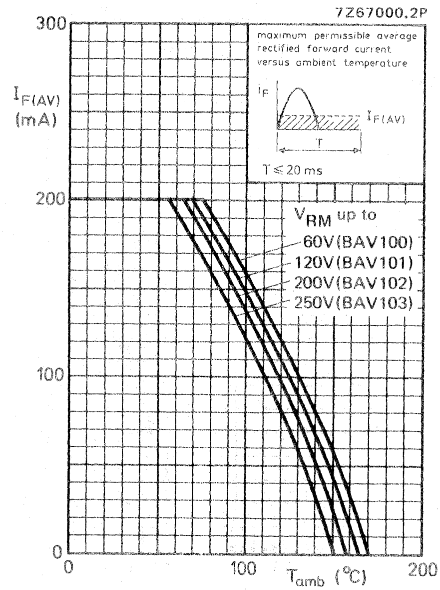


Fig. 8.

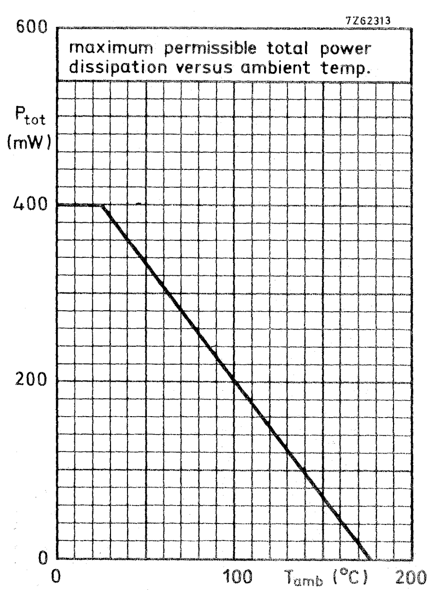


Fig. 9.

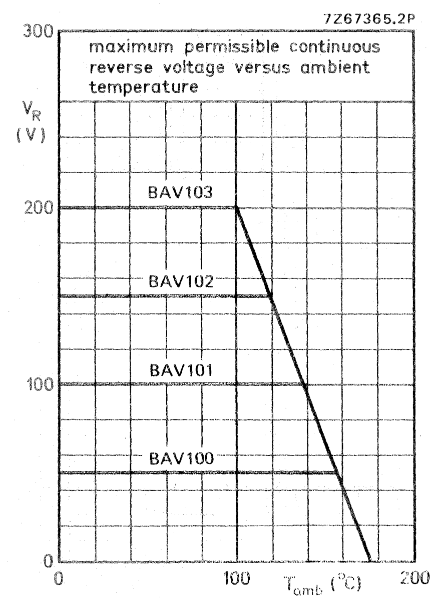


Fig. 10.

DEVELOPMENT DATA

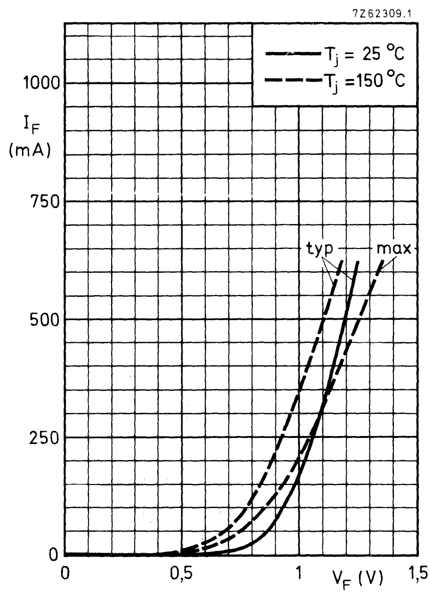


Fig. 11.

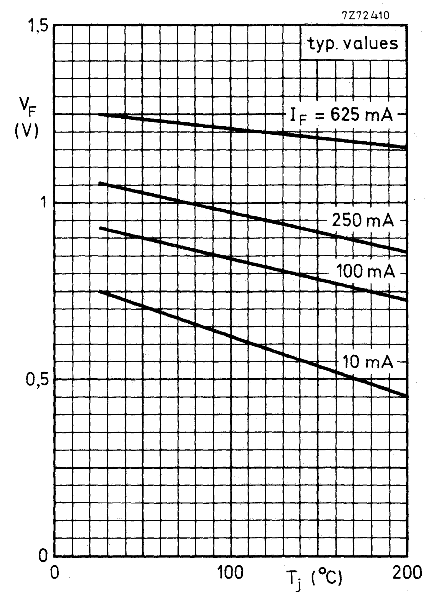


Fig. 12.

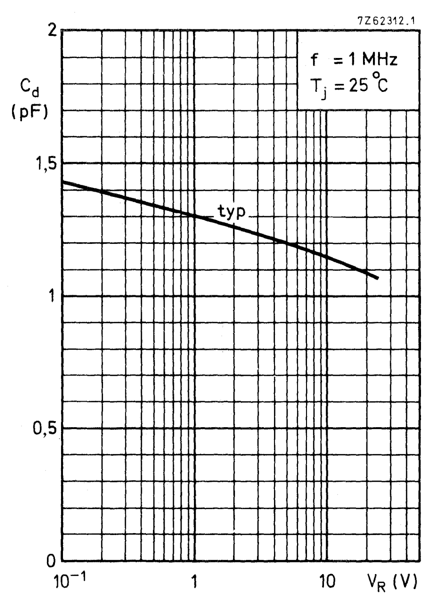


Fig. 13.

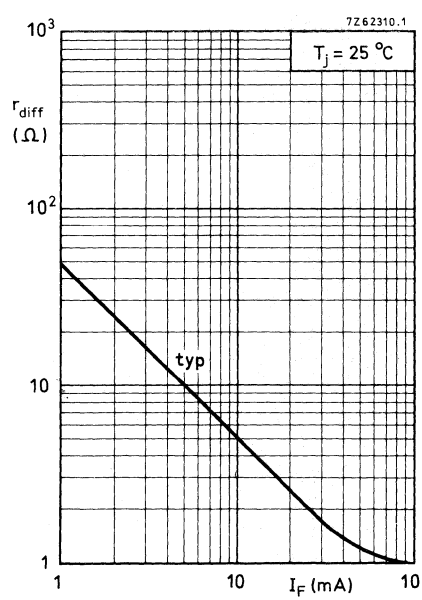


Fig. 14.

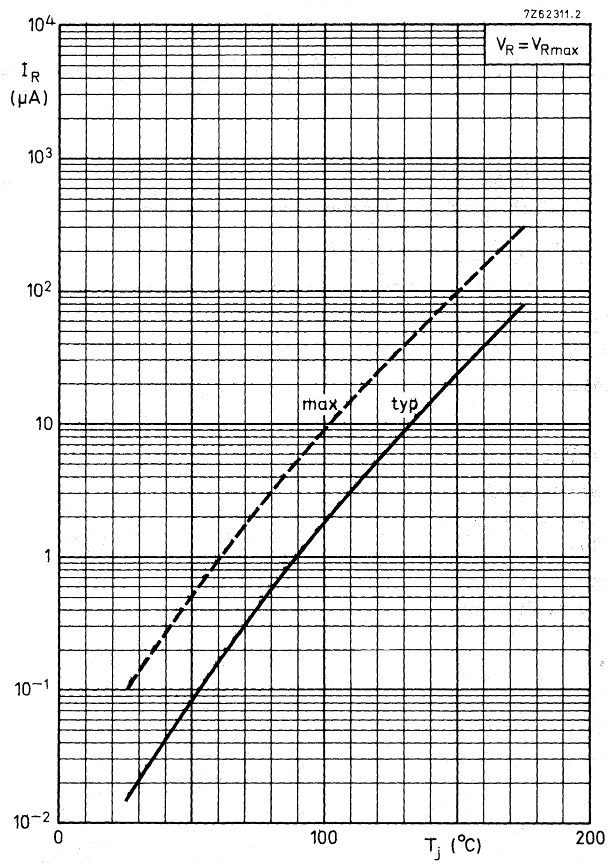

7Z62311.2
$V_R = V_{Rmax}$
I_R
(μA)
10^4
10^3
10^2
10
1
10^{-1}
10^{-2}
max
typ
0
100
200
T_j (°C)

Fig. 15.

SILICON PLANAR EPITAXIAL HIGH-SPEED DIODES

The BAW56 consists of two diodes in a microminiature plastic envelope. The anodes are commoned and the unit is intended for high-speed switching in thick and thin-film circuits.

QUICK REFERENCE DATA (per diode)

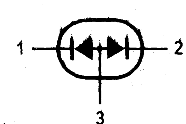
Continuous reverse voltage	V_R	max.	70	V
Repetitive peak reverse voltage	V_{RRM}	max.	70	V
Repetitive peak forward current	I_{FRM}	max.	250	mA
Junction temperature	T_j	max.	175	^oC
Forward voltage at I_F = 50 mA	V_F	<	1,0	V
Reverse recovery time when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<	6	ns
Recovery charge when switched from I_F = 10 mA to V_R = 5 V; R_L = 500 Ω	Q_s	<	45	pC

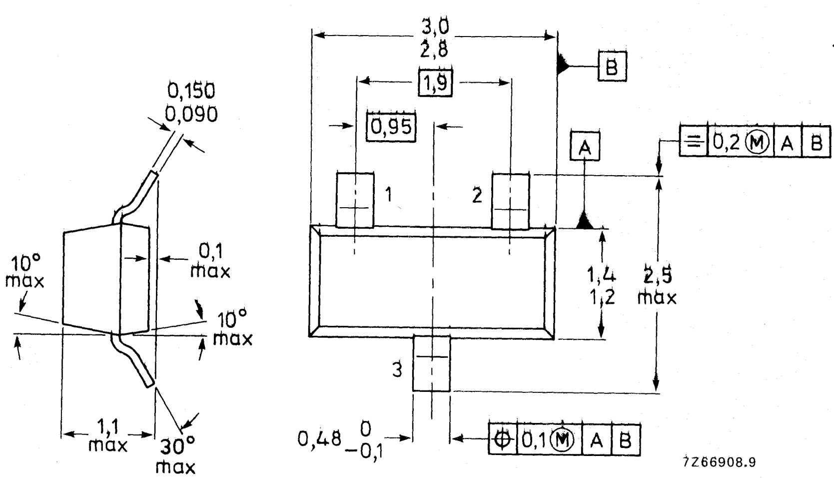
MECHANICAL DATA Dimensions in mm

Fig. 1 SOT-23.

Marking code

BAW56 = A1





TOP VIEW

See also *Soldering recommendations.*

RATINGS (per diode)

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	70 V
Repetitive peak reverse voltage	V_{RRM}	max.	70 V
Average rectified forward current▲ (averaged over any 20 ms period)	$I_{F(AV)}$	max.	250 mA
Forward current (d.c.)	I_F	max.	250 mA
Repetitive peak forward current	I_{FRM}	max.	250 mA
→ Non-repetitive peak forward current (per crystal)			
$t = 1\ \mu s$	I_{FSM}	max.	2 A
$t = 1$ ms	I_{FSM}	max.	1 A
$t = 1$ s	I_{FSM}	max.	0,5 A
Storage temperature range	T_{stg}		−65 to + 175 °C
Junction temperature	T_j	max.	175 °C

THERMAL RESISTANCE*

From junction to tab	$R_{th\ j\text{-}t}$	=	60 K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	2 x 280 K/W
From soldering points to ambient **	$R_{th\ s\text{-}a}$	=	2 x 90 K/W

CHARACTERISTICS (per diode)

$T_j = 25\ ^{\circ}C$ unless otherwise specified

Forward voltage			
$I_F = 1$ mA	V_F	<	715 mV
$I_F = 10$ mA	V_F	<	855 mV
$I_F = 50$ mA	V_F	<	1000 mV
$I_F = 150$ mA	V_F	<	1250 mV
Reverse current			
$V_R = 25$ V; $T_j = 150\ ^{\circ}C$	I_R	<	30 μA
$V_R = 70$ V	I_R	<	2,5 μA
$V_R = 70$ V; $T_j = 150\ ^{\circ}C$	I_R	<	50 μA
Diode capacitance			
$V_R = 0$; f = 1 MHz	C_d	<	2 pF
Forward recovery voltage when switched to			
$I_F = 10$ mA; $t_r = 20$ ns	V_{fr}	<	1,75 V

▲ Measured under pulse conditions: pulse time $t_p \leqslant 0{,}5$ ms.
For sinusoidal operation $I_{F(AV)} = 150$ mA; averaging time $t_{(av)} \leqslant 1$ ms.

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

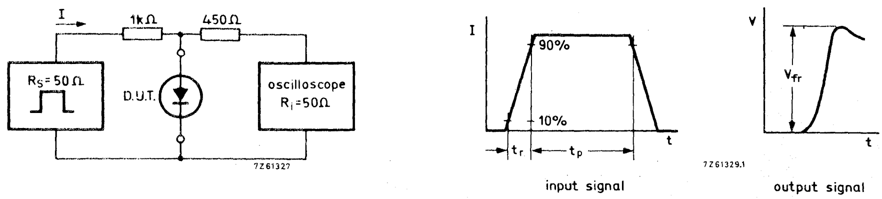


Fig. 2 Test circuit and waveforms; forward recovery voltage.

Input signal: Rise time of the forward pulse t_r = 20 ns
Forward current pulse duration t_p = 120 ns. Duty factor δ = 0,01
Oscilloscope: Rise time t_r = 0,35 ns.

Circuit capacitance $C \leqslant 1$ pF (C = oscilloscope input capacitance + parasitic capacitance)

Reverse recovery time when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA	t_{rr}	<	6 ns

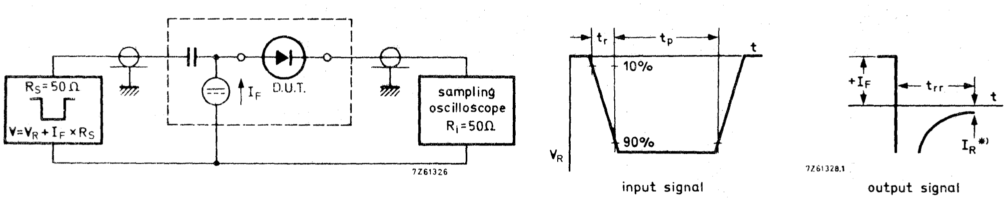


Fig. 3 Test circuit and waveforms; reverse recovery time.

*) I_R = 1 mA

Input signal: Rise time of the reverse pulse t_r = 0,6 ns
Reverse pulse duration t_p = 100 ns. Duty factor δ = 0,05.
Oscilloscope: Rise time t_r = 0,35 ns

Circuit capacitance $C \leqslant 1$ pF (C = oscilloscope input capacitance + parasitic capacitance)

Recovery charge when switched from I_F = 10 mA to V_R = 5 V; R_L = 500 Ω	Q_s	<	45 pC

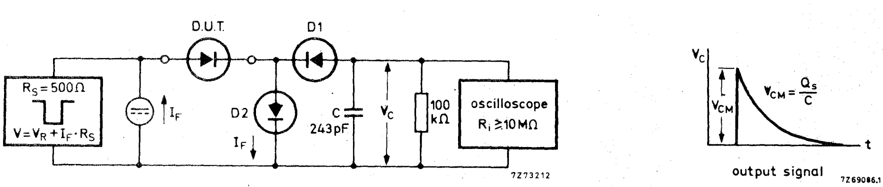


Fig. 4 Test circuit and waveform; recovery charge.

D2 = diode with minority carrier life time at 10 mA: < 200 ps. D1 = BAW62.

Input signal: Rise time of the reverse pulse t_r = 2 ns
Reverse pulse duration t_p = 400 ns. Duty factor δ = 0,02

Circuit capacitance $C \leqslant 7$ pF (C = oscilloscope input capacitance + parasitic capacitance).

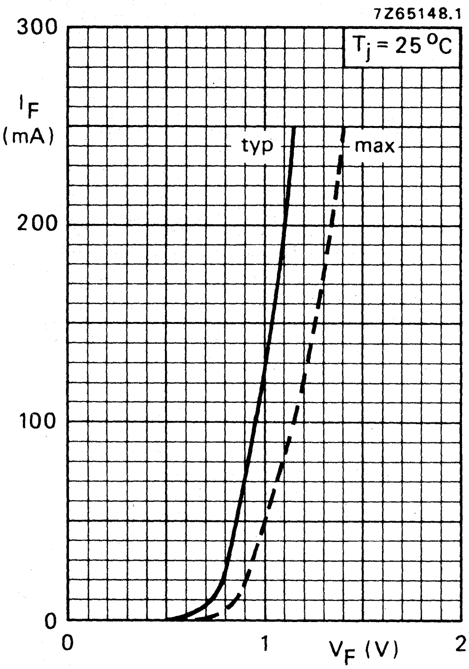


Fig. 5.

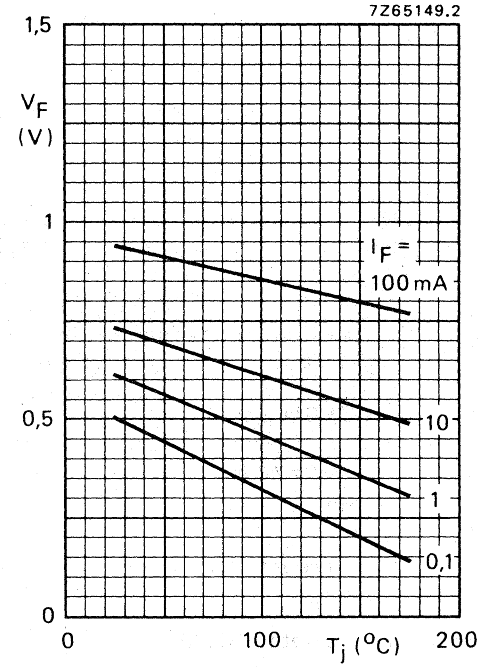


Fig. 6 Typical values.

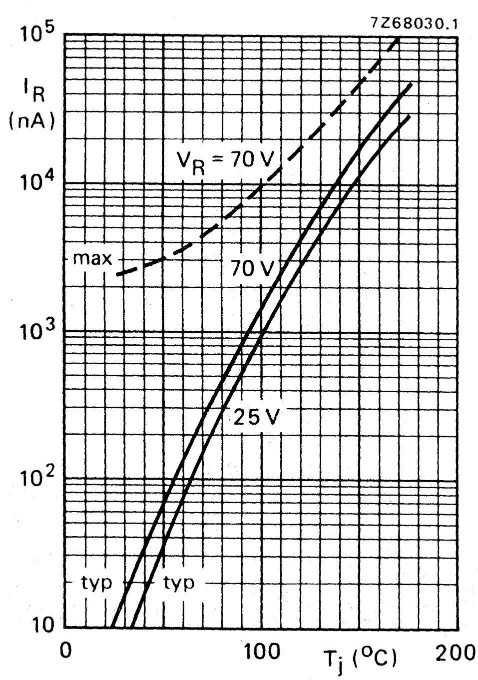


Fig. 7.

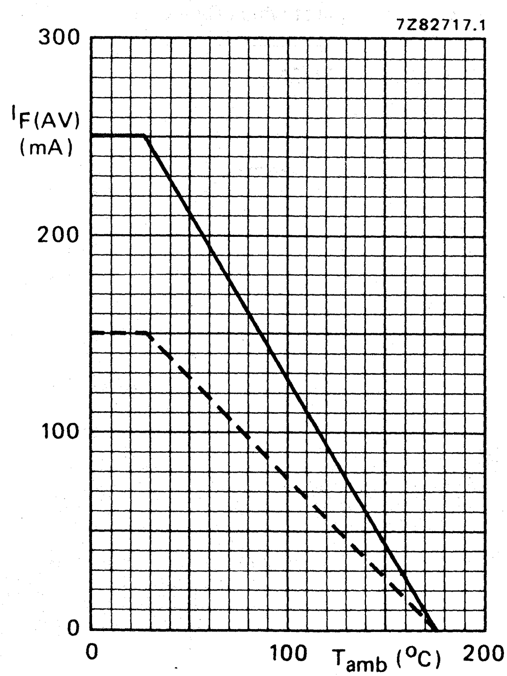


Fig. 8 ——— single diode;
– – – – double diode, equally loaded.

U.H.F. VARIABLE CAPACITANCE DIODE

The BB215 is a silicon variable capacitance diode in a hermetically sealed glass envelope (SOD-80) and intended for application in u.h.f. tuners. The leadless SOD-80 encapsulation is intended for surface mounting.
The diode features a capacitance characteristic with a good linearity.

Diodes are supplied in matched sets and the capacitance difference between any two diodes in one set is less than 3% over the voltage range from 0,5 V to 28 V.

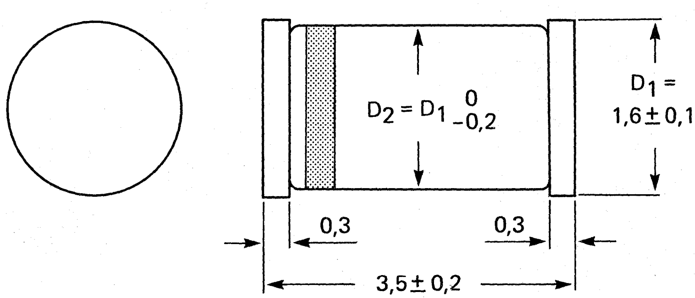
QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	30 V
Reverse current V_R = 28 V	I_R	<	10 nA
Diode capacitance at f = 500 kHz V_R = 28 V	C_d		1,8 to 2,2 pF
Capacitance ratio at f = 500 kHz	$\frac{C_d(V_R = 1\ V)}{C_d(V_R = 28\ V)}$	>	7,6
Series resistance at f = 470 MHz V_R is that value at which C_d = 9 pF	r_s	typ.	0,63 Ω

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-80.



The cathode is indicated by a white band on the body and a second green band indicates the BB215 type.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	30	V
Forward current (d.c.)	I_F	max.	20	mA
Storage temperature	T_{stg}		−55 to +150	°C
Operating junction temperature	T_j	max.	100	°C

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Reverse current				
V_R = 28 V	I_R	<	10	nA
V_R = 28 V; T_{amb} = 85 °C	I_R	<	200	nA
Diode capacitance at f = 500 kHz				
V_R = 1 V	C_d	typ.	17	pF
		<	18	pF
V_R = 3 V	C_d	typ.	11	pF
V_R = 28 V	C_d		1,8 to 2,2	pF
Capacitance ratio at f = 500 kHz	$\frac{C_d(V_R = 1\ V)}{C_d(V_R = 28\ V)}$	>	7,6	
		typ.	8,3	
Series resistance at f = 470 MHz and at that value of V_R at which C_d = 9 pF	r_s	typ.	0,63	Ω

V.H.F. VARIABLE CAPACITANCE DIODE

The BB219 is a silicon variable capacitance diode in a hermetically sealed glass envelope (SOD-80) and intended for electronic tuning in v.h.f. television tuners for C.A.T.V. applications.
The SOD-80 envelope is suitable for surface mounting.

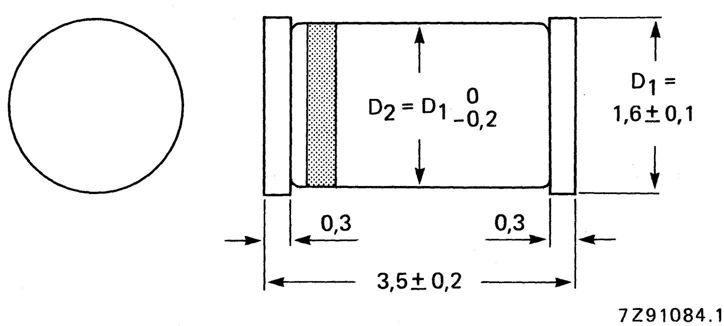
QUICK REFERENCE DATA

Reverse voltage, peak value	V_{RM}	max.	30 V
Reverse current V_R = 28 V	I_R	<	10 nA
Diode capacitance at f = 1 MHz V_R = 1 V	C_d	>	31 pF
V_R = 28 V	C_d		2,6 to 3,2 pF
Capacitance ratio at f = 1 MHz	$\frac{C_d(V_R = 1\ V)}{C_d(V_R = 28\ V)}$		12 to 15
Series resistance at f = 100 MHz V_R is that value at which C_d = 30 pF	r_s	typ.	0,7 Ω
		<	0,9 Ω

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-80.



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Reverse voltage, peak value	V_{RM}	max.	30 V ←
Forward current (d.c.)	I_F	max.	20 mA
Storage temperature	T_{stg}		−55 to +150 °C
Operating junction temperature	T_j	max.	100 °C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j\text{-}a}$	=	0,6 K/mW

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Reverse current			
V_R = 28 V	I_R	<	10 nA
V_R = 28 V; T_{amb} = 85 °C	I_R	<	200 nA
Diode capacitance at f = 0,5 MHz			
V_R = 1 V	C_d	>	31 pF
V_R = 3 V	C_d	typ.	24 pF
V_R = 28 V	C_d		2,6 to 3,2 pF
Capacitance ratio at f = 1 MHz	$\frac{C_d(V_R = 1\ V)}{C_d(V_R = 28\ V)}$		12 to 15
Series resistance at f = 100 MHz and at that value of V_R at which C_d = 30 pF	r_s	typ.	0,7 Ω
	r_s	<	0,9 Ω
Tolerance of capacitance difference between two diodes at V_R = 1 to 28 V	$\frac{\Delta C}{C}$	<	2,5 %

VARIABLE CAPACITANCE DIODE

Silicon planar variable capacitance diode in a microminiature envelope. It is intended for electronic tuning applications in thick and thin-film circuits.

QUICK REFERENCE DATA

Reverse voltage	V_R	max.	28 V
Reverse current at V_R = 28 V	I_R	<	50 nA
Diode capacitance at f = 1 MHz V_R = 25 V	C_d		1,8 to 2,8 pF
Capacitance ratio at f = 1 MHz	$\frac{C_d\ (V_R = 3\ V)}{C_d\ (V_R = 25\ V)}$	typ.	5
Series resistance at f = 470 MHz V_R = that value at which C_d = 9 pF	r_D	<	1,2 Ω

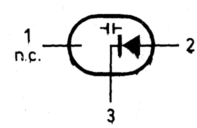
MECHANICAL DATA

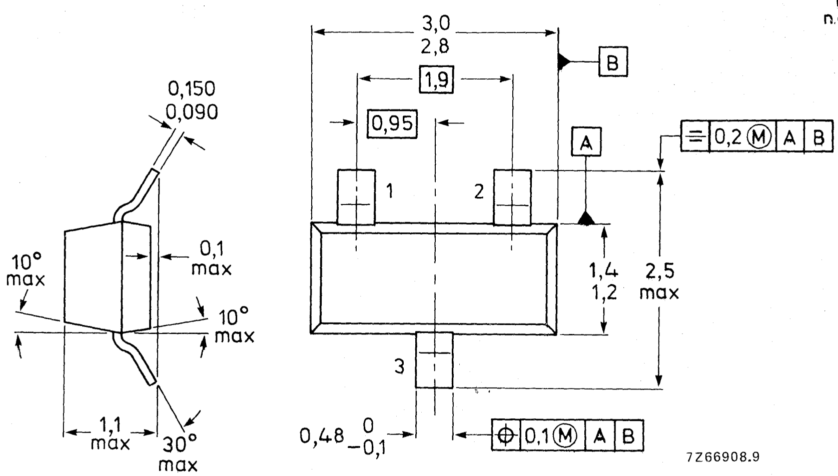
Dimensions in mm

Fig. 1 SOT-23.

Marking code

BBY31 = S1





TOP VIEW

See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	28 V
Reverse voltage (peak value)	V_{RM}	max.	30 V
Forward current (d.c.)**	I_F	max.	20 mA
Storage temperature	T_{stg}	−65 to + 100 °C	
Operating junction temperature	T_j	max.	85 °C

THERMAL RESISTANCE

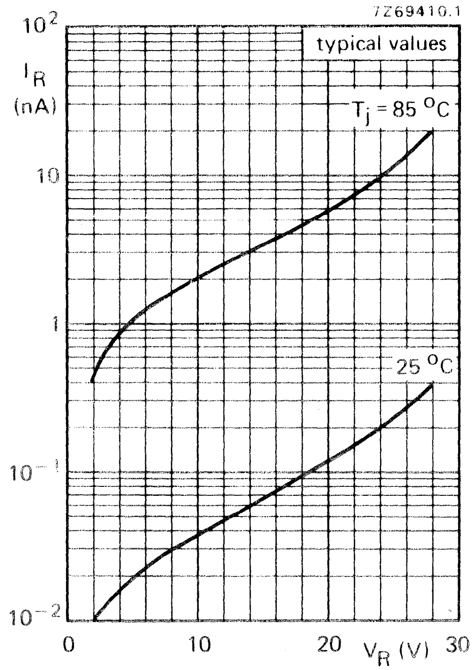
→ From junction to ambient*	$R_{th\ j\text{-}a}$	=	430 K/W

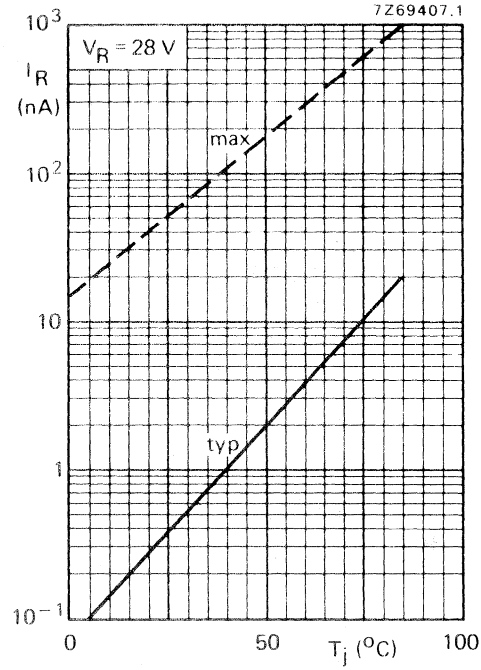
CHARACTERISTICS

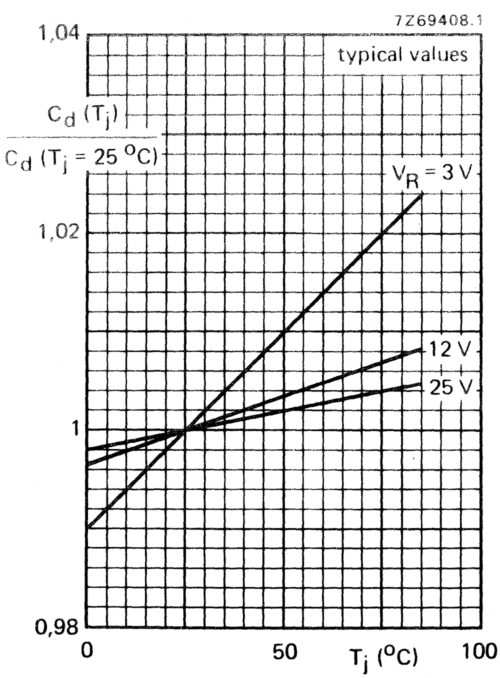
T_j = 25 °C unless otherwise specified

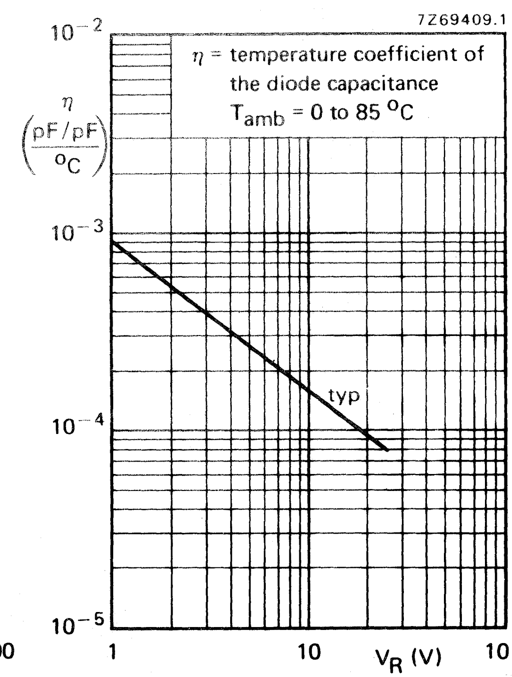
Reverse current			
V_R = 28 V	I_R	<	50 nA
V_R = 28 V; T_j = 85 °C	I_R	<	1000 nA
Diode capacitance at f = 1 MHz			
V_R = 1 V	C_d	typ.	17,5 pF
V_R = 3 V	C_d	typ.	11,5 pF
V_R = 25 V	C_d		1,8 to 2,8 pF
Capacitance ratio at f = 1 MHz	$\frac{C_d\ (V_R = 3\ V)}{C_d\ (V_R = 25\ V)}$	typ.	5
Series resistance at f = 470 MHz and at that value of V_R at which C_d = 9 pF	r_D	<	1,2 Ω

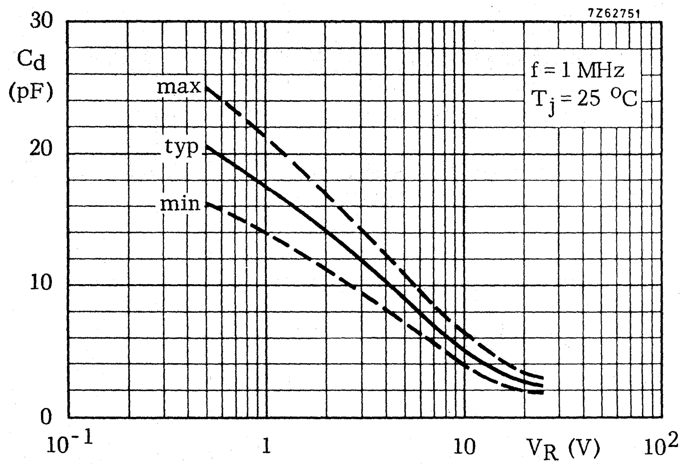
* Mounted on a ceramic substrate of 7 mm x 5 mm x 0,5 mm.


7Z69410.1
typical values
I_R (nA)
T_j = 85 °C
25 °C
V_R (V)
10^2
10
1
10^-1
10^-2
0
10
20
30


7Z69407.1
V_R = 28 V
I_R (nA)
max
typ
T_j (°C)
10^3
10^2
10
1
10^-1
0
50
100


7Z69408.1
typical values
$\frac{C_d (T_j)}{C_d (T_j = 25\ °C)}$
V_R = 3 V
12 V
25 V
T_j (°C)
1,04
1,02
1
0,98
0
50
100


7Z69409.1
η = temperature coefficient of the diode capacitance
T_{amb} = 0 to 85 °C
η (pF/pF / °C)
typ
V_R (V)
10^-2
10^-3
10^-4
10^-5
1
10
10^2


7Z62751
30
C_d
(pF)
20
10
0
max
typ
min
f = 1 MHz
T_j = 25 °C
10^{-1}
1
10
V_R (V)
10^2

SILICON PLANAR VARIABLE CAPACITANCE DIODE

The BBY40 is a variable capacitance diode in a plastic envelope intended for electronic tuning in v.h.f. television tuners with extended band I (FCC and OIRT-norm).

QUICK REFERENCE DATA

Continuous reverse voltage	V_R	max.	28 V
Reverse current at V_R = 28 V	I_R	<	50 nA
Diode capacitance at f = 1 MHz			
V_R = 3 V	C_d		26 to 32 pF
V_R = 25 V	C_d		4,3 to 6 pF
Capacitance ratio at f = 1 MHz	$\frac{C_d (V_R = 3\ V)}{C_d (V_R = 25\ V)}$		5 to 6,5
Series resistance at f = 200 MHz V_R is that value at which C_d = 25 pF	r_D	<	0,6 Ω

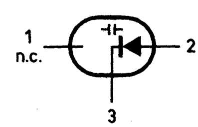
MECHANICAL DATA

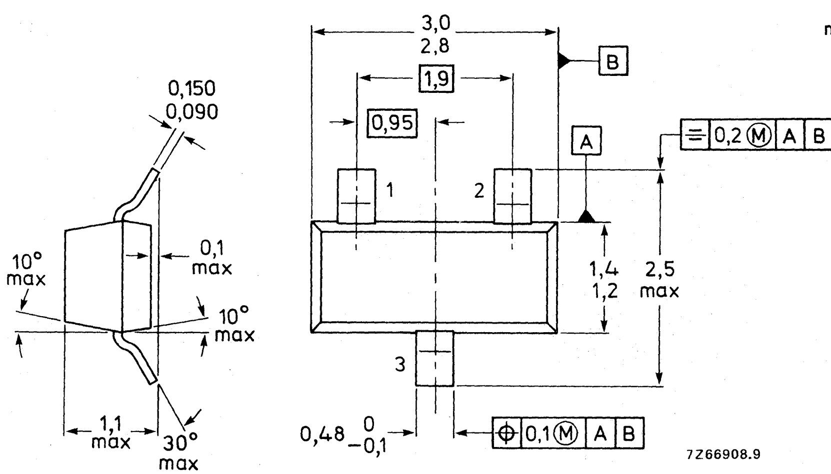
Dimensions in mm

Fig. 1 SOT-23.

Marking code

BBY40 = S2





TOP VIEW

See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	V_R	max.	28 V
Reverse voltage (repetitive peak value)	V_{RRM}	max.	30 V
Forward current (d.c.)	I_F	max.	20 mA
Storage temperature	T_{stg}		−55 to + 100 °C
Operating junction temperature	T_j	max.	85 °C

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j\text{-}a}$	=	430 K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Reverse current			
V_R = 28 V	I_R	typ.	0,1 nA
		<	50 nA
V_R = 28 V; T_{amb} = 60 °C	I_R	<	500 nA
Diode capacitance at f = 1 MHz			
V_R = 3 V	C_d		26 to 32 pF
V_R = 25 V	C_d		4,3 to 6 pF
Capacitance ratio at f = 1 MHz	$\frac{C_d\ (V_R = 3\ V)}{C_d\ (V_R = 25\ V)}$		5 to 6,5
Series resistance at f = 200 MHz			
V_R is that value at which C_d = 25 pF	r_D	typ.	0,4 Ω
		<	0,6 Ω

* Mounted on a ceramic substrate of 7 mm x 5 mm x 0,5 mm.

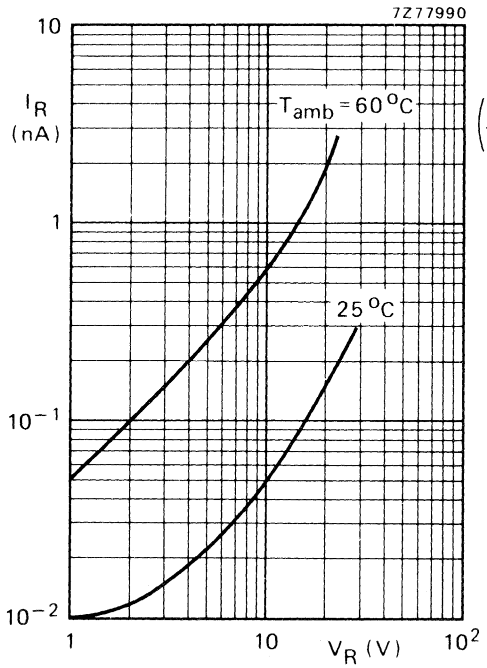


Fig. 2 Typical values

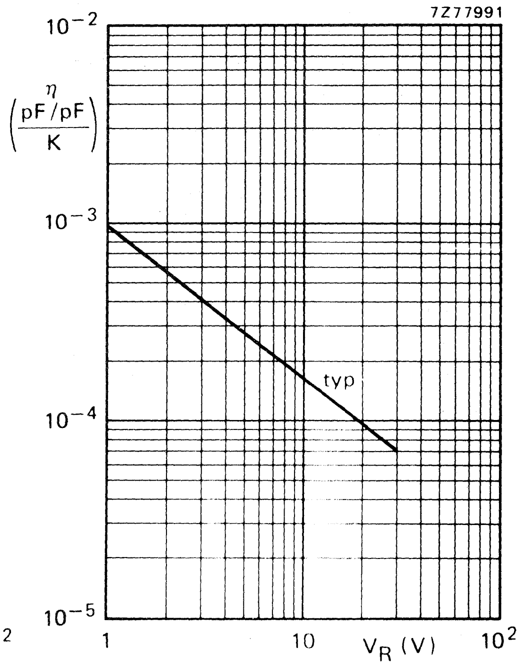


Fig. 3 Temperature coefficient of the diode capacitance; T_{amb} = 0 to 85 °C.

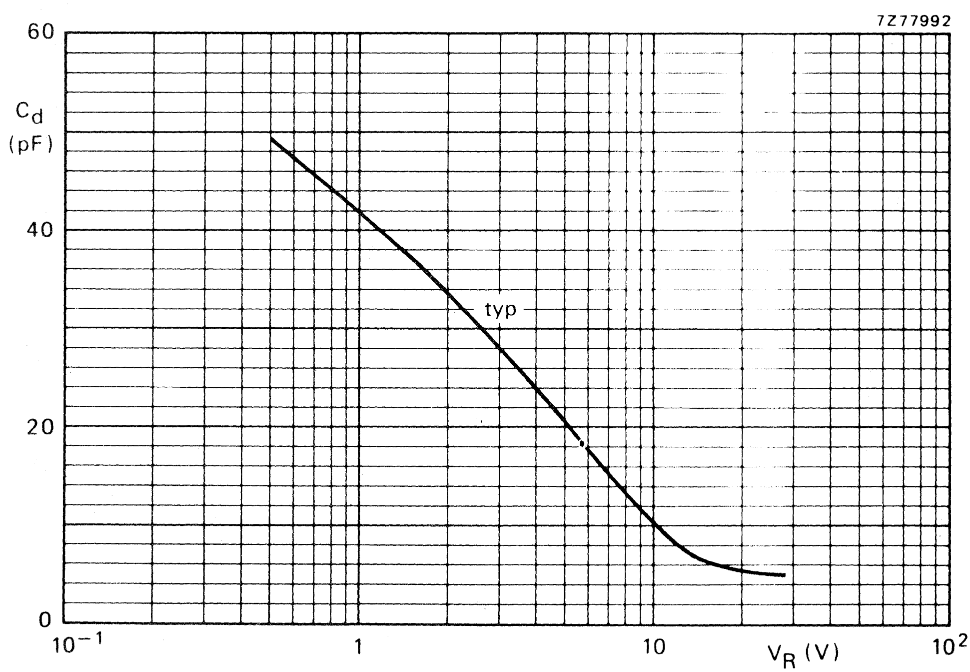


Fig. 4 f = 1 MHz; T_{amb} = 25 °C.

SILICON PLANAR EPITAXIAL TRANSISTORS

P-N-P transistors, in a SOT-23 plastic envelope for use in driver and output stages of audio amplifiers in thick and thin-film hybrid circuits.

N-P-N complements are BC817; R and BC818; R respectively.

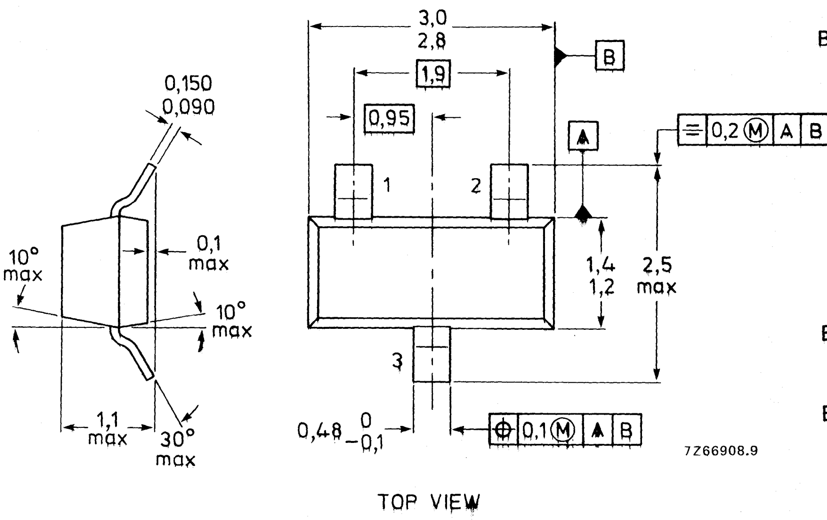
QUICK REFERENCE DATA

			BC807	BC808	
Collector-emitter voltage (V_{BE} = 0)	$-V_{CES}$	max.	50	30	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	45	25	V
Collector current (peak value)	$-I_{CM}$	max.	1000		mA
Total power dissipation up to T_{amb} = 35 °C	P_{tot}	max.	310		mW
Junction temperature	T_j	max.	150		°C
Transition frequency at f = 35 MHz $-I_C$ = 10 mA; $-V_{CE}$ = 5 V	f_T	typ.	100		MHz

MECHANICAL DATA

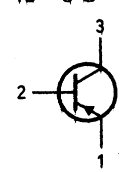
Dimensions in mm

Fig. 1 SOT-23.

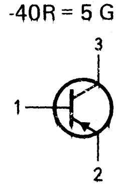


Marking code

BC807-16 = 5 A
-25 = 5 B
-40 = 5 C
BC808-16 = 5 E
-25 = 5 F
40 = 5 G



BC807-16R = 5 AR
-25R = 5 BR
-40R = 5 CR
BC808-16R = 5 ER
-25R = 5 FR
-40R = 5 GR



R-types are available on request.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BC807	BC808	
Collector-emitter voltage ($V_{BE} = 0$)	$-V_{CES}$	max.	50	30	V
Collector-emitter voltage (open base) $-I_C = 10$ mA	$-V_{CEO}$	max.	45	25	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5	5	V
Collector current (d.c.)	$-I_C$	max.	500		mA
Collector current (peak value)	$-I_{CM}$	max.	1000		mA
Emitter current (peak value)	I_{EM}	max.	1000		mA
Base current (d.c.)	$-I_B$	max.	100		mA
Base current (peak value)	$-I_{BM}$	max.	200		mA
Total power dissipation at $T_{amb} = 35\ ^oC$ *	P_{tot}	max.	310		mW
Storage temperature	T_{stg}		−65 to + 150		^oC
Junction temperature	T_j	max.	150		^oC

THERMAL CHARACTERISTICS **

$T_j = P\ (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	50	K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	260	K/W
From soldering points to ambient *	$R_{th\ s\text{-}a}$	=	60	K/W

* Mounted on a ceramic substrate of 15 mm x 15 mm x 0,7 mm.

** See *Thermal characteristics.*

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current			
$I_E = 0$; $-V_{CB} = 20$ V; $T_j = 25$ °C	$-I_{CBO}$	<	100 nA
$I_E = 0$; $-V_{CB} = 20$ V; $T_j = 150$ °C	$-I_{CBO}$	<	5 μA
Emitter cut-off current			
$I_C = 0$; $V_{EB} = 5$ V	$-I_{EBO}$	<	10 μA
Base emitter voltage *			
$-I_C = 500$ mA; $-V_{CE} = 1$ V	$-V_{BE}$	<	1,2 V
Saturation voltage			
$-I_C = 500$ mA; $-I_B = 50$ mA	$-V_{CEsat}$	<	700 mV
D.C. current gain			
$-I_C = 500$ mA; $-V_{CE} = 1$ V	h_{FE}	>	40
$-I_C = 100$ mA; $-V_{CE} = 1$ V; BC807; BC808	h_{FE}		100 to 600
BC807-16, BC808-16	h_{FE}		100 to 250
BC807-25, BC808-25	h_{FE}		160 to 400
BC807-40, BC808-40	h_{FE}		250 to 600
Transition frequency at f = 35 MHz			
$-I_C = 10$ mA; $-V_{CE} = 5$ V	f_T	typ.	100 MHz
Collector capacitance at f = 1 MHz			
$I_E = I_e = 0$; $-V_{CB} = 10$ V	C_c	typ.	8 pF

* $-V_{BE}$ decreases by about 2 mV/K with increasing temperature.

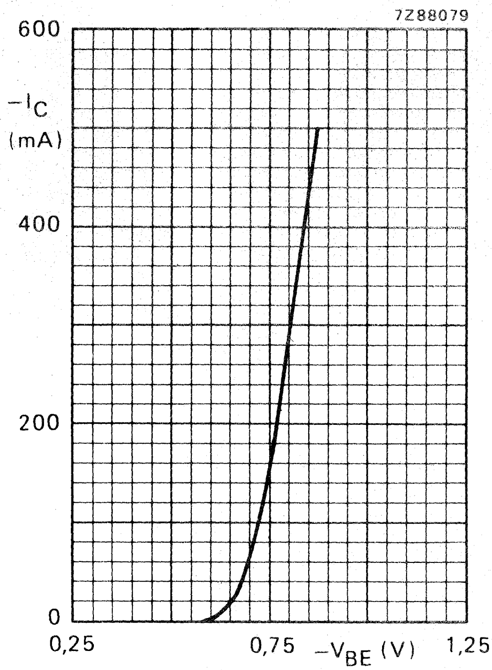


Fig. 2 $-V_{CE}$ = 1 V; T_j = 25 °C.
Typical values.

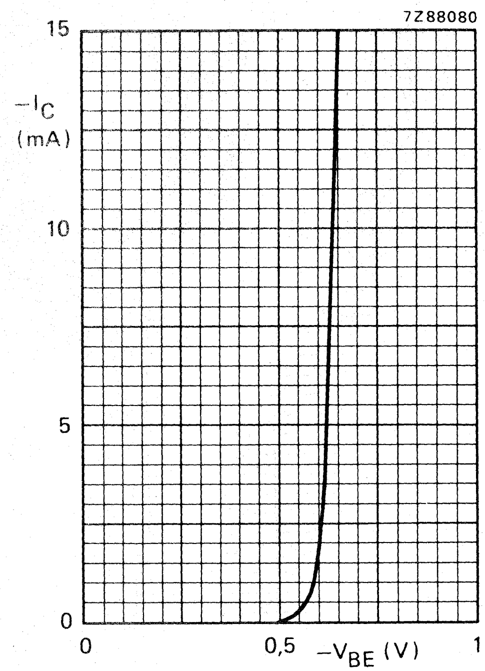


Fig. 3 $-V_{CE}$ = 5 V; T_j = 25 °C.
Typical values.

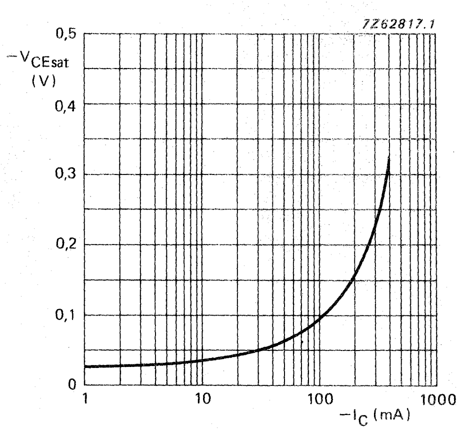


Fig. 4 typical values.

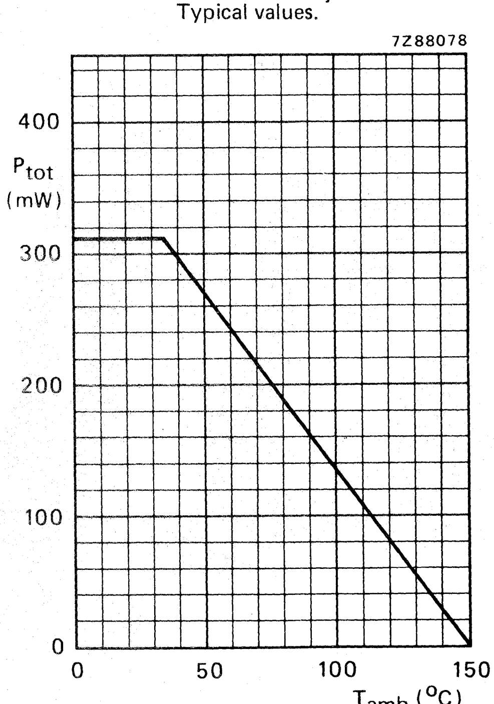


Fig. 5. Power derating curve.

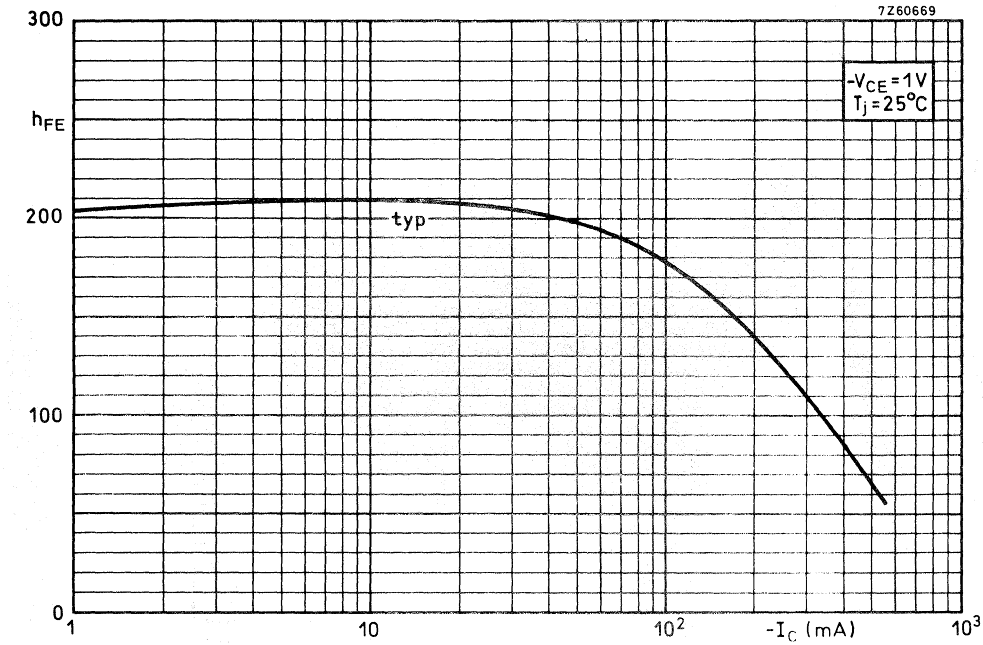


Fig. 6 D.C. current gain.

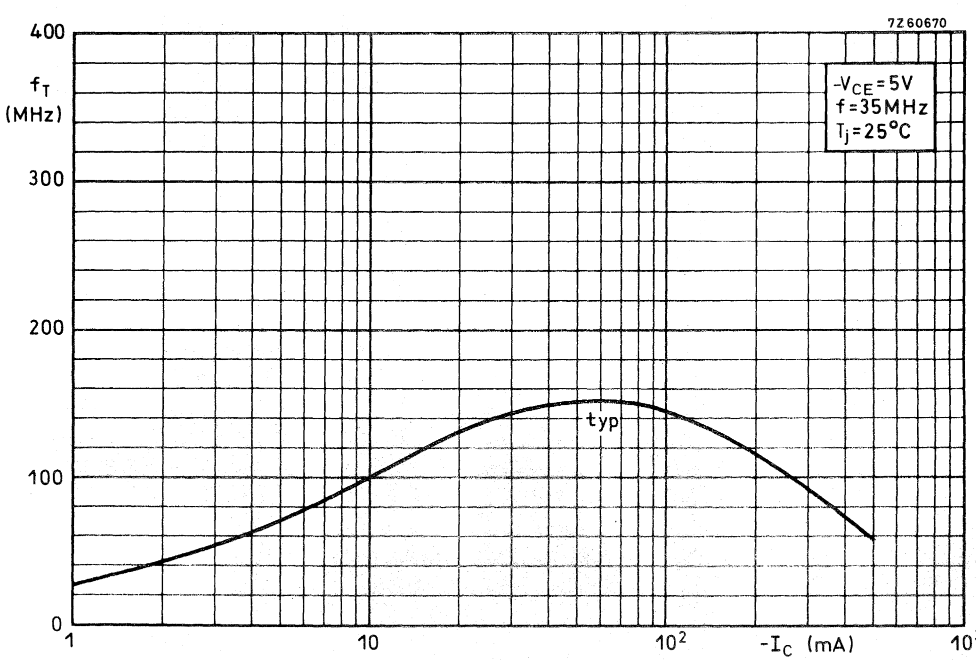


Fig. 7 Typical values transition frequency.

SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N transistors, in a SOT-23 plastic envelope for use in driver and output stages of audio amplifiers in thick and thin-film hybrid circuits.

P-N-P complements are BC807; R and BC808; R respectively.

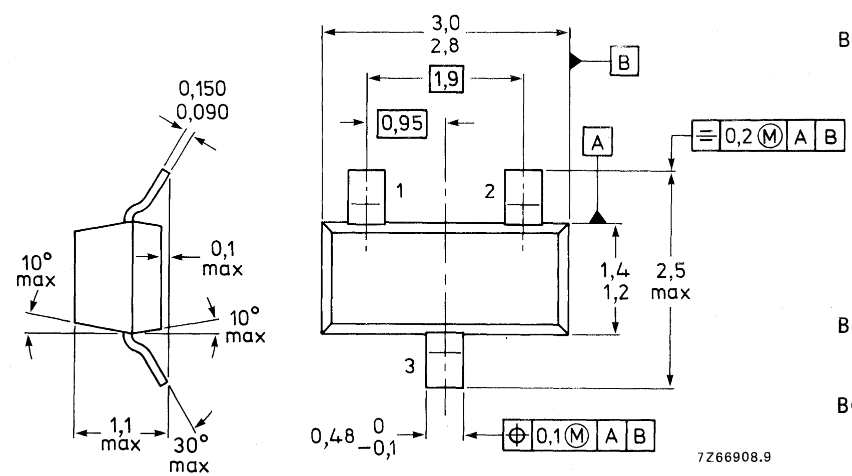
QUICK REFERENCE DATA

			BC817	BC818	
Collector-emitter voltage (V_{BE} = 0)	V_{CES}	max.	50	30	V
Collector-emitter voltage (open base)	V_{CEO}	max.	45	25	V
Collector current (peak value)	I_{CM}	max.	1000		mA
Total power dissipation up to T_{amb} = 35 °C	P_{tot}	max.	310		mW
Junction temperature	T_j	max.	150		°C
Transition frequency at f = 35 MHz; I_C = 10 mA; V_{CE} = 5 V	f_T	typ.	200		MHz

MECHANICAL DATA

Dimensions in mm

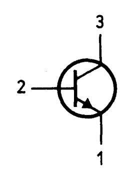
Fig. 1 SOT-23.



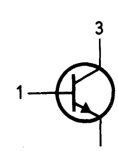
TOP VIEW

Marking code

BC817-16 = 6 A
-25 = 6 B
-40 = 6 C
BC818-16 = 6 E
-25 = 6 F
-40 = 6 G



BC817-16R = 6 AR
-25R = 6 BR
-40R = 6 CR
BC818-16R = 6 ER
-25R = 6 FR
-40R = 6 GR



R-types are available on request.

See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BC817	BC818	
Collector-emitter voltage (V_{BE} = 0)	V_{CES}	max.	50	30	V
Collector-emitter voltage (open base) I_C = 10 mA	V_{CEO}	max.	45	25	V
Emitter-base voltage (open collector)	V_{EBO}	max.	5	5	V

Collector current (d.c.)	I_C	max.	500	mA
Collector current (peak value)	I_{CM}	max.	1000	mA
Emitter current (peak value)	$-I_{EM}$	max.	1000	mA
Base current (d.c.)	I_B	max.	100	mA
Base current (peak value)	I_{BM}	max.	200	mA
Total power dissipation up to T_{amb} = 35 ^oC	P_{tot}	max.	310	mW
Storage temperature	T_{stg}		−65 to + 150	^oC
Junction temperature	T_j	max.	150	^oC

THERMAL CHARACTERISTICS **

$T_j = P\,(R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	50	K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	260	K/W
From soldering points to ambient *	$R_{th\ s\text{-}a}$	=	60	K/W

* Mounted on a ceramic substrate of 15 mm x 15 mm x 0,7 mm.
** See *Thermal characteristics.*

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current			
$I_E = 0$; $V_{CB} = 20$ V; $T_j = 25$ °C	I_{CBO}	<	100 nA
$I_E = 0$; $V_{CB} = 20$ V; $T_j = 150$ °C	I_{CBO}	<	5 μA
Emitter cut-off current			
$I_C = 0$; $V_{EB} = 5$ V	I_{EBO}	<	10 μA
Base emitter voltage *			
$I_C = 500$ mA; $V_{CE} = 1$ V	V_{BE}	<	1,2 V
Saturation voltage			
$I_C = 500$ mA; $I_B = 50$ mA	V_{CEsat}	<	700 mV
D.C. current gain			
$I_C = 500$ mA; $V_{CE} = 1$ V	h_{FE}	>	40
$I_C = 100$ mA; $V_{CE} = 1$ V; BC817; BC818	h_{FE}		100 to 600
BC817-16, BC818-16	h_{FE}		100 to 250
BC817-25, BC818-25	h_{FE}		160 to 400
BC817-40, BC818-40	h_{FE}		250 to 600
Transition frequency at f = 35 MHz			
$I_C = 10$ mA; $V_{CE} = 5$ V	f_T	typ.	200 MHz
Collector capacitance at f = 1 MHz			
$I_E = I_e = 0$; $V_{CB} = 10$ V	C_c	typ.	5 pF

* V_{BE} decreases by about 2 mV/K with increasing temperature.

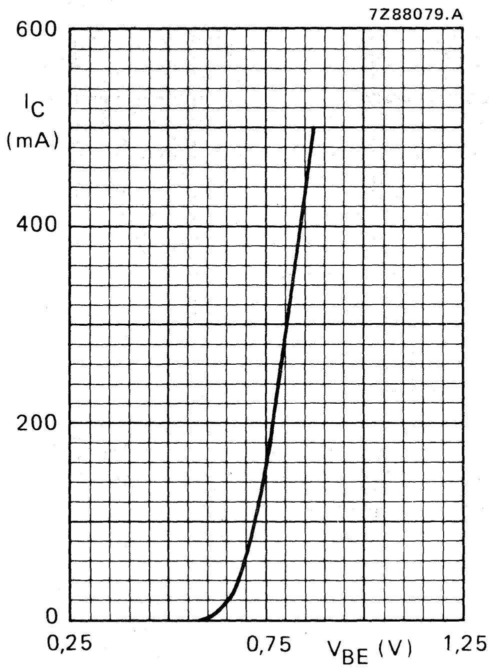


Fig. 2 V_{CE} = 1 V; T_j = 25 °C. Typical values.

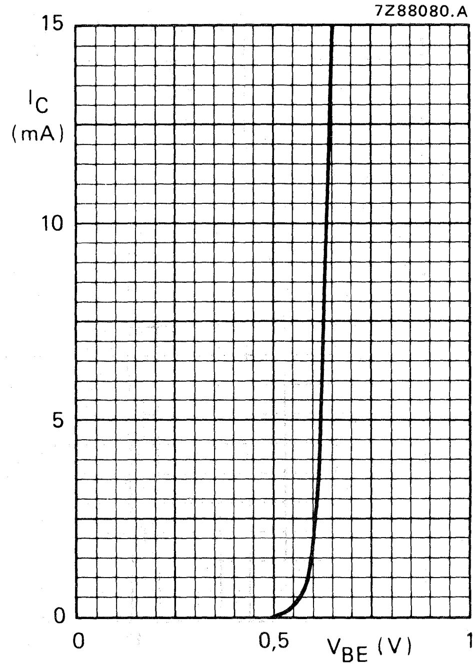


Fig. 3 V_{CE} = 5 V; T_j = 25 °C. Typical values.

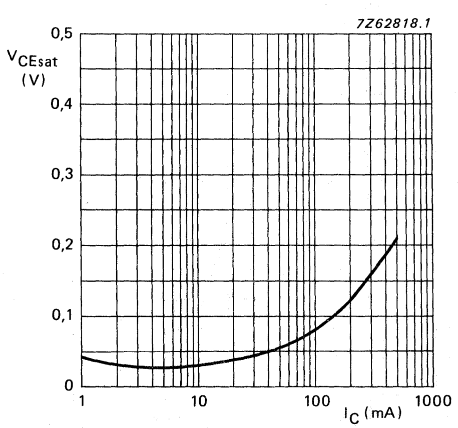


Fig. 4 I_C/I_B = 10; T_j = 25 °C.

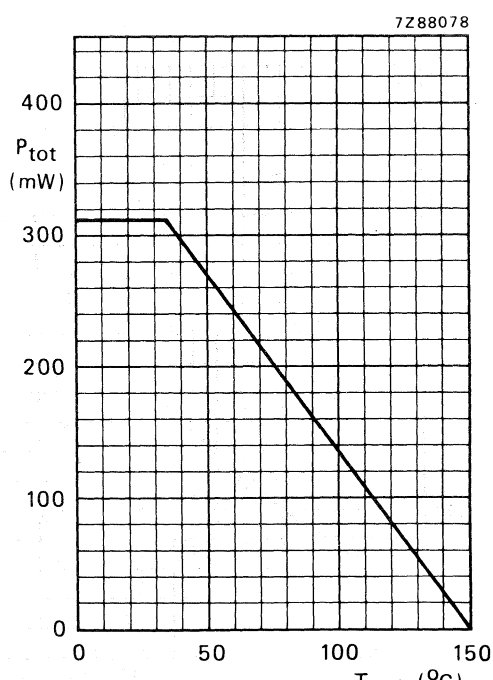


Fig. 5 Power derating curve.

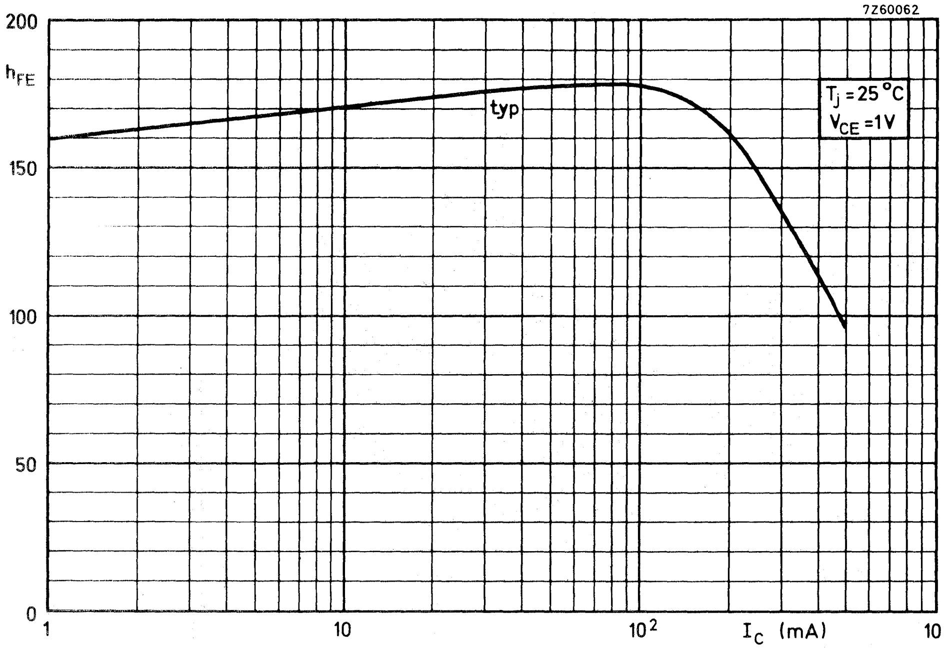


Fig. 6 D.C. current gain.

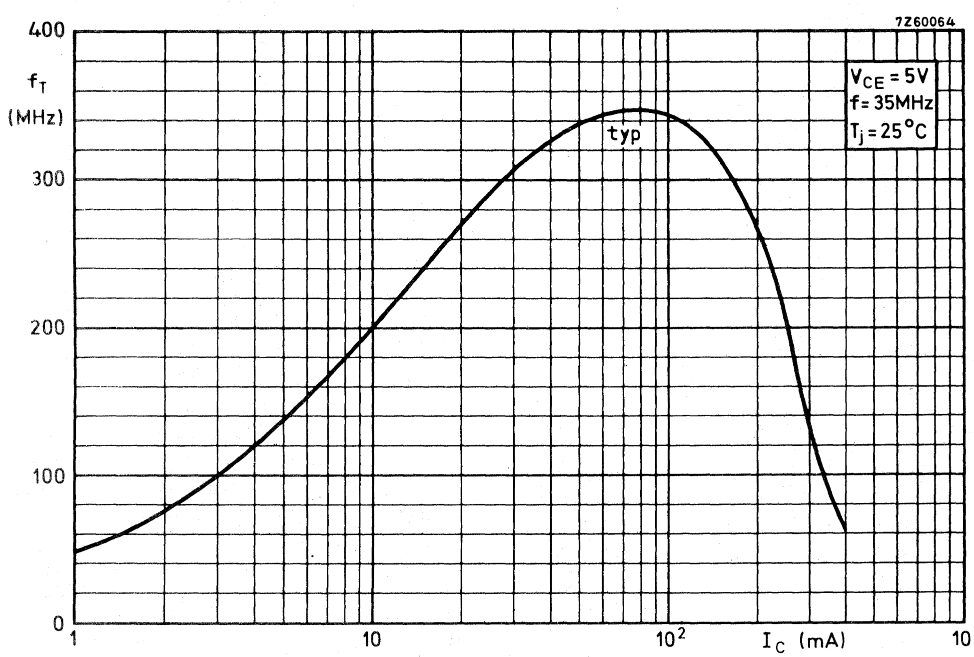


Fig. 7 Typical values transition frequency.

SILICON PLANAR EPITAXIAL TRANSISTORS

General purpose n-p-n transistors in a plastic SOT-23 variant, especially suitable for use in driver stages of audio amplifiers in thick and thin-film hybrid circuits.

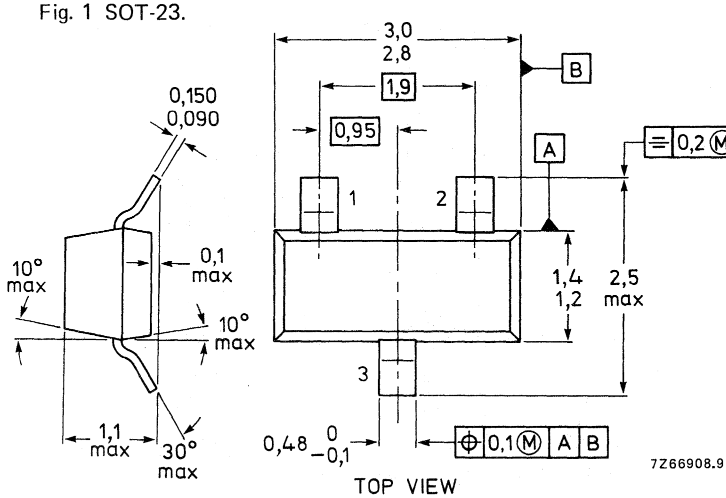
QUICK REFERENCE DATA

			BC846	BC847	BC848	
Collector-emitter voltage (V_{BE} = 0)	V_{CES}	max.	80	50	30	V
Collector-emitter voltage (open base)	V_{CEO}	max.	65	45	30	V
Collector current (peak value)	I_{CM}	max.	200	200	200	mA
Total power dissipation up to T_{amb} = 60 °C	P_{tot}	max.	200	200	200	mW
Junction temperature	T_j	max.	150	150	150	°C
Small-signal current gain I_C = 2 mA; V_{CE} = 5 V; f = 1 kHz	h_{fe}	>	125	125	125	
		<	500	900	900	
Transition frequency I_C = 10 mA; V_{CE} = 5 V	f_T	typ.	300	300	300	MHz
Noise figure at R_S = 2 kΩ I_C = 200 μA; V_{CE} = 5 V f = 1 kHz; B = 200 Hz	F	typ.	2	2	2	dB

MECHANICAL DATA

Dimensions in mm

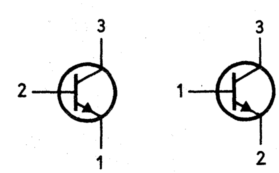
Fig. 1 SOT-23.



Marking code

		type	reverse
BC846A	=	1A	1AR
B	=	1B	1BR
BC847A	=	1E	1ER
B	=	1F	1FR
C	=	1G	1GR
BC848A	=	1J	1JR
B	=	1K	1KR
C	=	1L	1LR

type : reverse:



R-types are available on request

See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BC846	BC847	BC848	
Collector-base voltage (open emitter)	V_{CBO}	max.	80	50	30	V
Collector-emitter voltage ($V_{BE} = 0$)	V_{CES}	max.	80	50	30	V
Collector-emitter voltage (open base)	V_{CEO}	max.	65	45	30	V
Emitter-base voltage (open collector)	V_{EBO}	max.	6	6	5	V

Collector current (d.c.)	I_C	max.	100	mA
Collector current (peak value)	I_{CM}	max.	200	mA
Emitter current (peak value)	$-I_{EM}$	max.	200	mA
Base current (peak value)	I_{BM}	max.	200	mA
Total power dissipation* up to T_{amb} = 60 °C	P_{tot}	max.	200	mW
Storage temperature	T_{stg}		−65 to + 150	°C
Junction temperature	T_j	max.	150	°C

THERMAL CHARACTERISTICS**

$$T_j = P (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	60	K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280	K/W
From soldering points to ambient*	$R_{th\ s\text{-}a}$	=	90	K/W

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

** See *Thermal characteristics.*

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current				
I_E = 0; V_{CB} = 30 V	I_{CBO}	<	15	nA
I_E = 0; V_{CB} = 30 V; T_j = 150 °C	I_{CBO}	<	5	μA
Base-emitter voltage*				
I_C = 2 mA; V_{CE} = 5 V	V_{BE}	typ.	660	mV
		580 to	700	mV
I_C = 10 mA; V_{CE} = 5 V	V_{BE}	<	770	mV
Saturation voltage**				
I_C = 10 mA; I_B = 0,5 mA	V_{CEsat}	typ.	90	mV
		<	250	mV
	V_{BEsat}	typ.	700	mV
I_C = 100 mA; I_B = 5 mA	V_{CEsat}	typ.	200	mV
		<	600	mV
	V_{BEsat}	typ.	900	mV
Collector capacitance at f = 1 MHz				
I_E = I_e = 0; V_{CB} = 10 V	C_c	typ.	2,5	pF
Transition frequency at f = 35 MHz				
I_C = 10 mA; V_{CE} = 5 V	f_T	typ.	300	MHz

* V_{BE} decreases by about 2 mV/K with increasing temperature.
** V_{BEsat} decreases by about 1,7 mV/K with increasing temperature.

			BC846	BC847	BC848	
Small signal current gain at f = 1 kHz						
I_C = 2 mA; V_{CE} = 5 V	h_{fe}	>	125	125	125	
		<	500	900	900	
Noise figure at R_S = 2 kΩ						
I_C = 200 μA; V_{CE} = 5 V; f = 1 kHz; B = 200 Hz	F	typ.	2	2	2	dB
		<	10	10	10	dB

			BC846A BC847A BC848A	BC846B BC847B BC848B	BC847C BC848C
D.C. current gain					
I_C = 10 μA; V_{CE} = 5 V	h_{FE}	typ.	90	150	270
		>	110	200	420
I_C = 2 mA; V_{CE} = 5 V	h_{FE}	typ.	180	290	520
		<	220	450	800

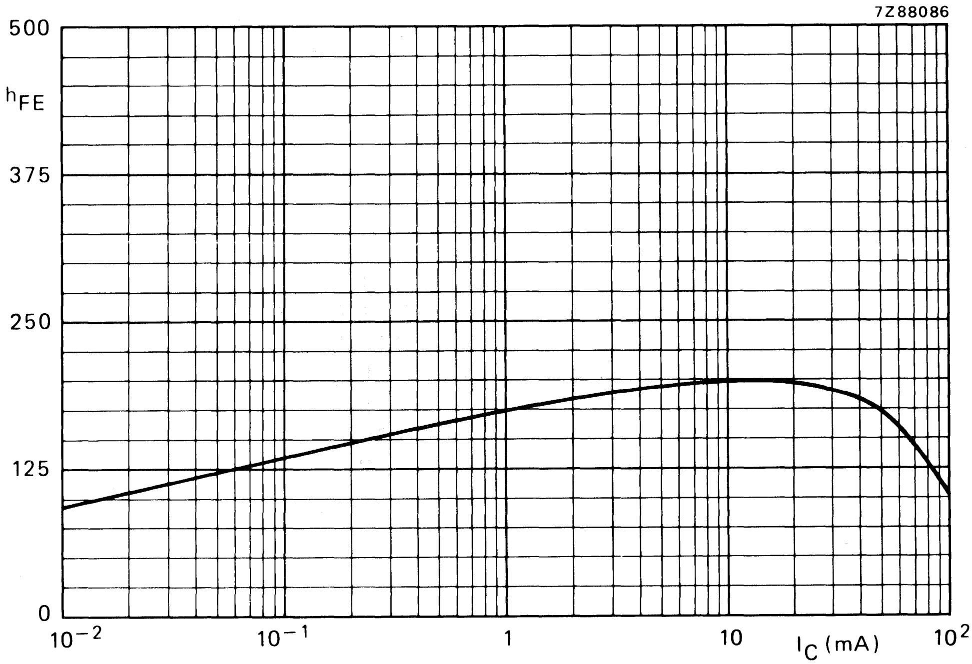


Fig. 3 Typical D.C. current gain for A-selections. V_{CE} = 5 V; T_j = 25 °C.

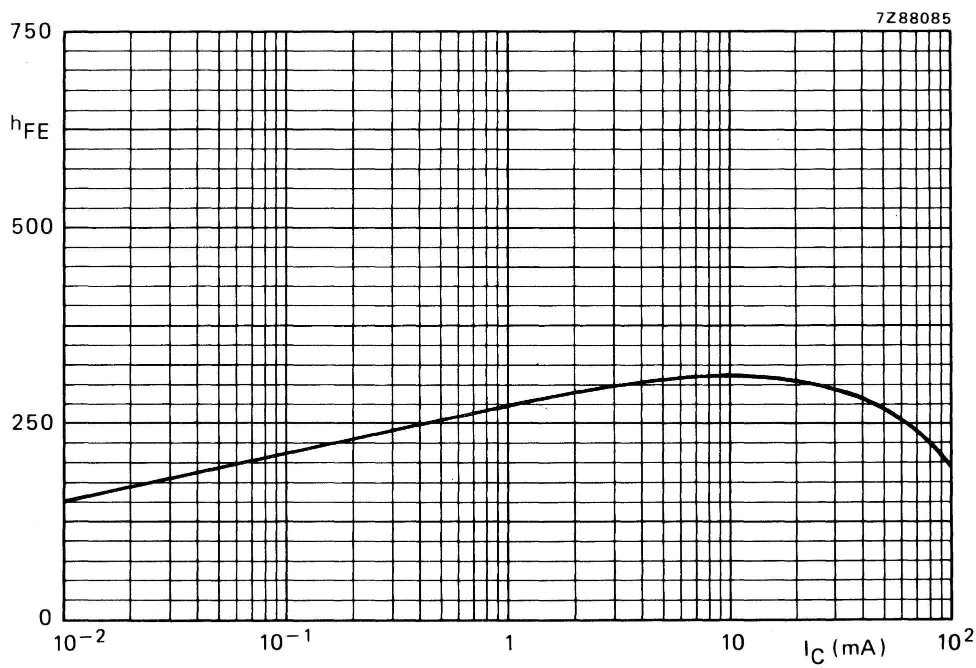


Fig. 4 Typical D.C. current gain for B-selections. V_{CE} = 5 V; T_j = 25 °C.

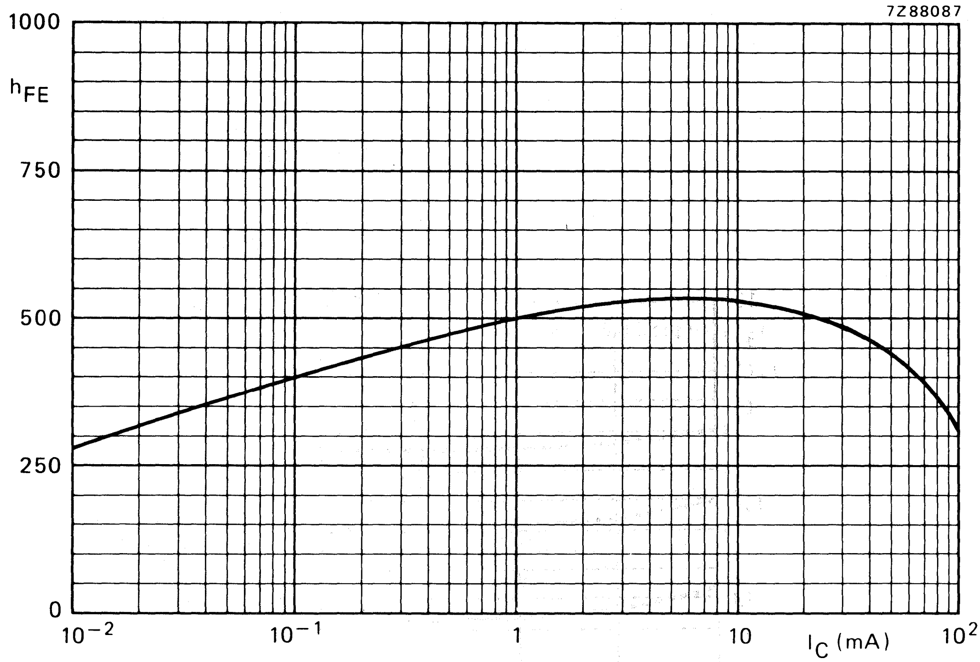


Fig. 5 Typical D.C. current gain for C-selections. V_{CE} = 5 V; T_j = 25 °C.

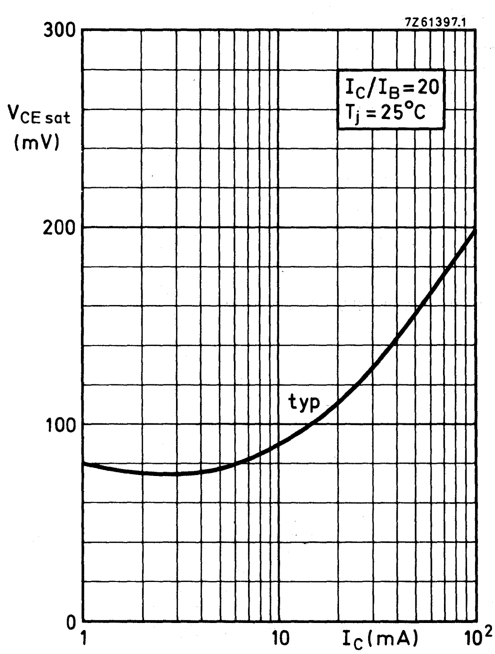


Fig. 6 Typical values.

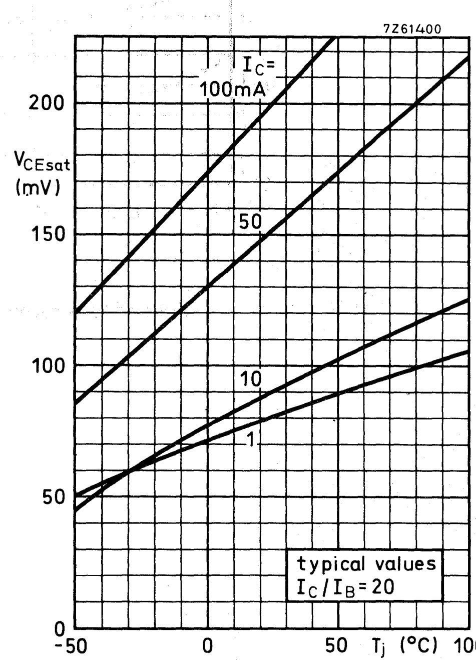


Fig. 7 Typical values.

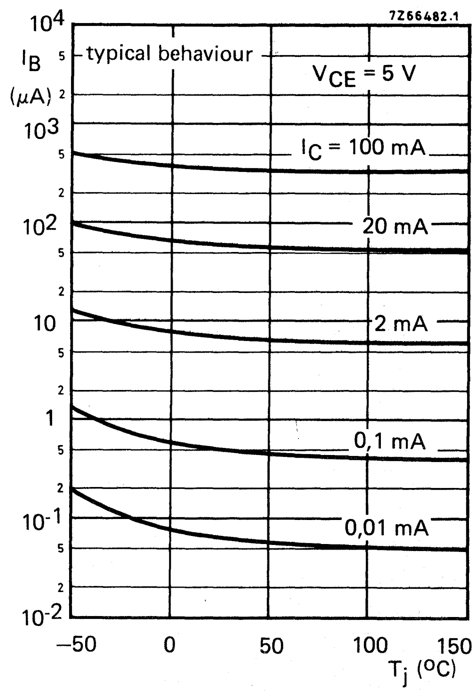


Fig. 8 Typical behaviour of base current versus junction temperature.

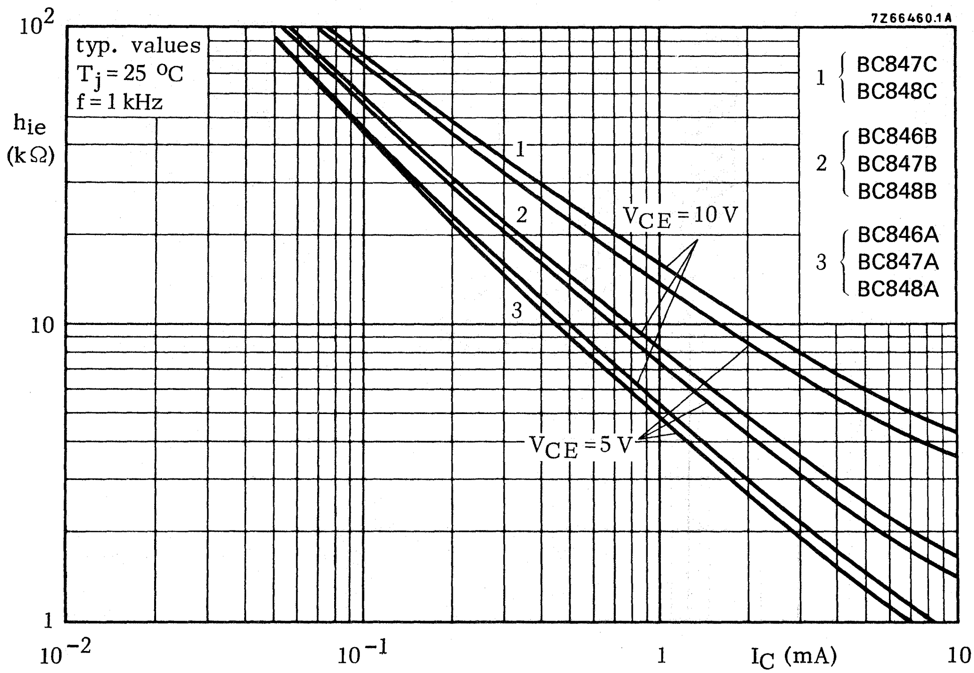


Fig. 9 Input impedance. 1 = C selections; 2 = B selections; 3 = A selections.

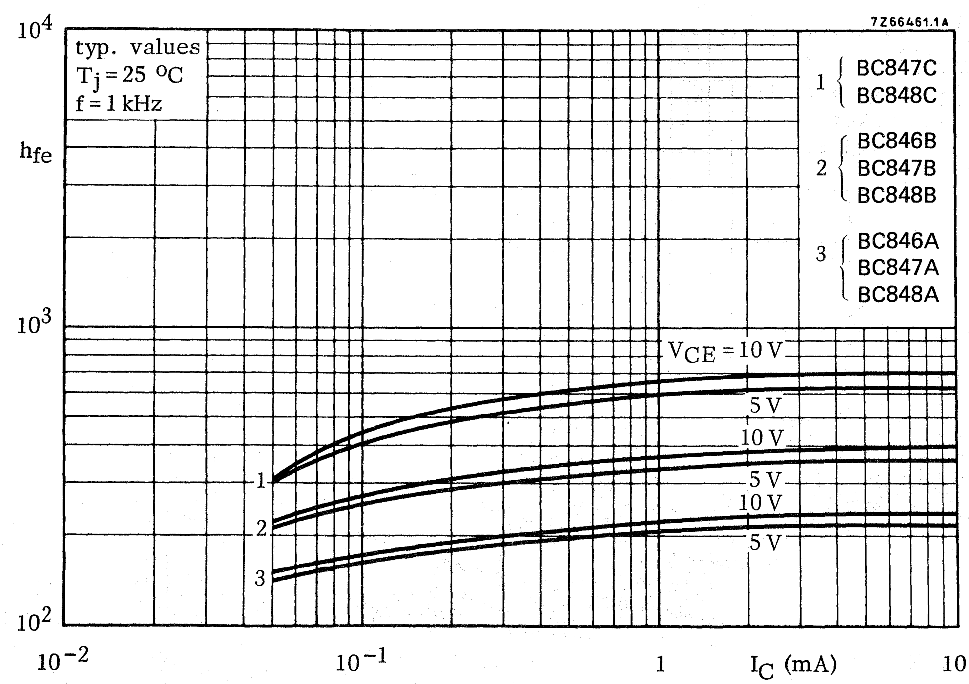


Fig. 10 Small signal current gain. 1 = C-; 2 = B- and 3 = A-selections.

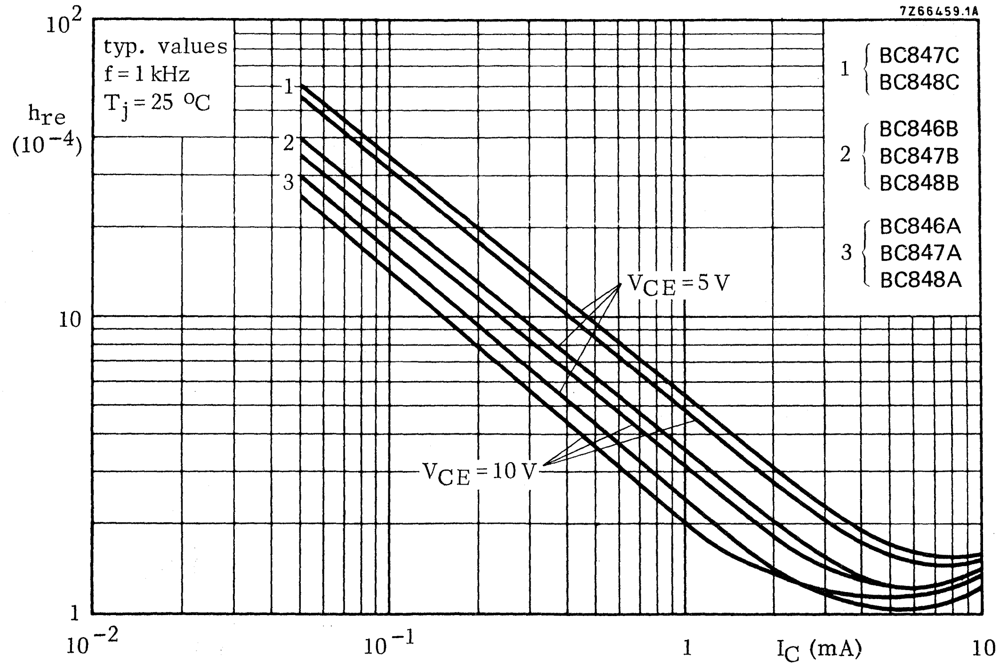


Fig. 11 Reverse voltage transfer ratio. 1 = C-; 2 = B- and 3 = A-selections.

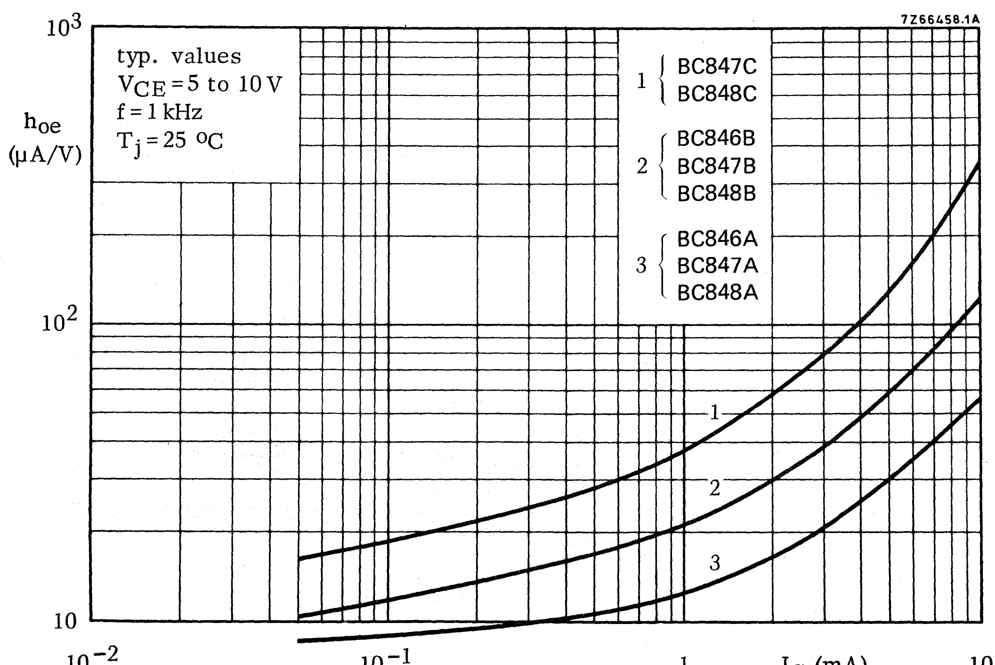


Fig. 12 Output admittance. 1 = C-; 2 = B- and 3 = A-selections.

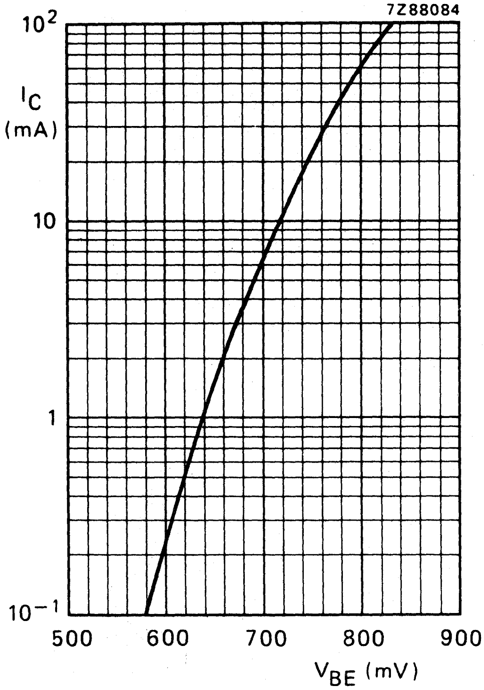


Fig. 13 Typical values at V_{CE} = 5 V; T_j = 25 °C.

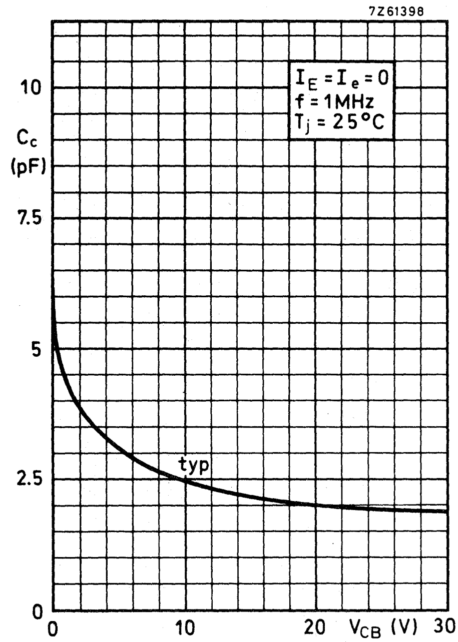


Fig. 14 Typical values.

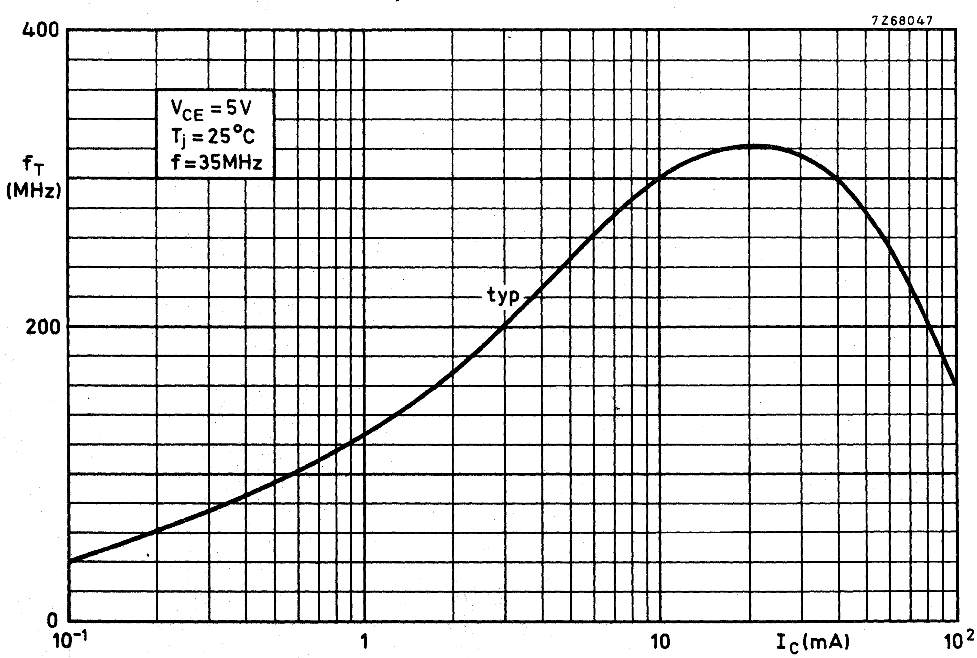


Fig. 15 Typical values transition frequency.

SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N transistors in a plastic SOT-23 envelope, primarily intended for low-noise input stages in tape recorders, hi-fi amplifiers and other audio-frequency equipment in thick and thin-film hybrid circuits.

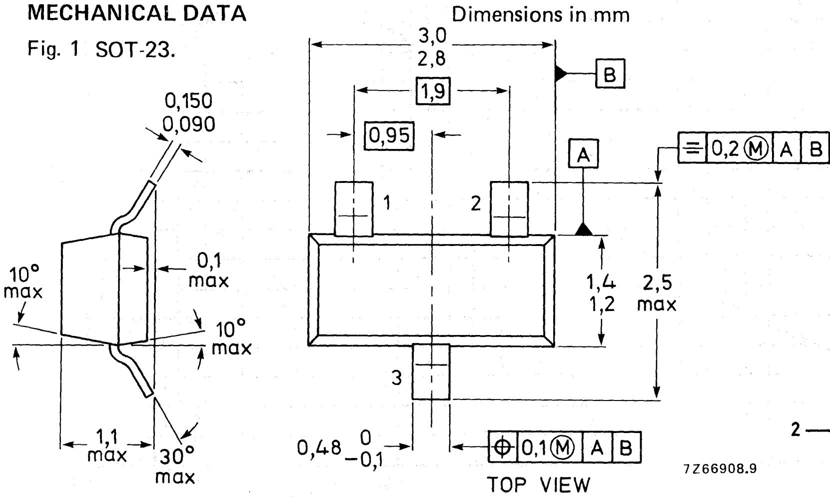
QUICK REFERENCE DATA

			BC849	BC850	
Collector-emitter voltage (V_{BE} = 0)	V_{CES}	max.	30	50	V
Collector-emitter voltage (open base)	V_{CEO}	max.	30	45	V
Collector current (peak value)	I_{CM}	max.	200	200	mA
Total power dissipation up to T_{amb} = 60 °C	P_{tot}	max.	200	200	mW
Junction temperature	T_j	max.	150	150	°C
Small-signal current gain I_C = 2 mA; V_{CE} = 5 V; f = 1 kHz	h_{fe}	> <	240 900	240 900	
Transition frequency I_C = 10 mA; V_{CE} = 5 V	f_T	typ.	300	300	MHz
Noise figure at R_S = 2 kΩ I_C = 200 μA; V_{CE} = 5 V f = 30 Hz to 15 kHz	F	typ. <	1,4 4	1,4 3	dB dB
f = 1 kHz; B = 200 Hz	F	typ.	1,2	1	dB
f = 10 Hz to 50 Hz (equivalent noise voltage)	V_n	<	–	0,135	μV

MECHANICAL DATA

Fig. 1 SOT-23.

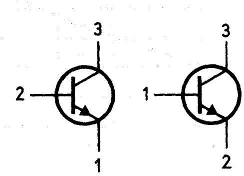
Dimensions in mm



Marking code

BC849B = 2B
BC849C = 2C
BC850B = 2F
BC850C = 2G

BC849BR = 2BR
BC849CR = 2CR
BC850BR = 2FR
BC850CR = 2GR



R-types are available on request

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BC849	BC850	
Collector-base voltage (open emitter)	V_{CBO}	max.	30	50	V
Collector-emitter voltage (V_{BE} = 0)	V_{CES}	max.	30	50	V
Collector-emitter voltage (open base)	V_{CEO}	max.	30	45	V
Emitter-base voltage (open collector)	V_{EBO}	max.	5	5	V

Collector current (d.c.)	I_C	max.	100	mA
Collector current (peak value)	I_{CM}	max.	200	mA
Emitter current (peak value)	$-I_{EM}$	max.	200	mA
Base current (peak value)	I_{BM}	max.	200	mA
Total power dissipation up to T_{amb} = 60 °C**	P_{tot}	max.	200	mW
Storage temperature	T_{stg}		−65 to + 150	°C
Junction temperature	T_j	max.	150	°C

THERMAL CHARACTERISTICS*

$T_j = Px\ (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	60	K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280	K/W
From soldering points to ambient**	$R_{th\ s\text{-}a}$	=	90	K/W

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current				
$I_E = 0$; $V_{CB} = 30$ V	I_{CBO}	<	15	nA
$I_E = 0$; $V_{CB} = 30$ V; $T_j = 150$ °C	I_{CBO}	<	5	μA
Base emitter voltage*				
$I_C = 2$ mA; $V_{CE} = 5$ V	V_{BE}	typ.	660	mV
		580 to	700	mV
$I_C = 10$ mA; $V_{CE} = 5$ V	V_{BE}	<	770	mV
Saturation voltages**				
$I_C = 10$ mA; $I_B = 0,5$ mA	V_{CEsat}	typ.	90	mV
		<	250	mV
	V_{BEsat}	typ.	700	mV
$I_C = 100$ mA; $I_B = 5$ mA	V_{CEsat}	typ.	200	mV
		<	600	mV
	V_{BEsat}	typ.	900	mV
Collector capacitance at f = 1 MHz				
$I_E = I_e = 0$; $V_{CB} = 10$ V	C_c	typ.	2,5	pF
Transition frequency at f = 35 MHz				
$I_C = 10$ mA; $V_{CE} = 5$ V	f_T	typ.	300	MHz

* V_{BE} decreases by about 2 mV/K with increasing temperature.
** V_{BEsat} decreases by about 1,7 mV/K with increasing temperature.

			BC849	BC850	
Small signal current gain at f = 1 kHz					
I_C = 2 mA; V_{CE} = 5 V	h_{fe}	>	240	240	
		<	900	900	
Noise figure at R_S = 2 kΩ					
I_C = 200 μA; V_{CE} = 5 V					
f = 30 Hz to 15 kHz	F	typ.	1,4	1,4	dB
		<	4	3	dB
f = 1 kHz; B = 200 Hz	F	typ.	1,2	1	dB
		<	4	4	dB
Equivalent noise voltage at R_S = 2 kΩ					
I_C = 200 μA; V_{CE} = 5 V					
f = 10 Hz to 50 Hz; T_{amb} = 25 °C	V_n	max.	–	0,135	μV

			B-selections	C-selections
D.C. current gain				
I_C = 10 μA; V_{CE} = 5 V	h_{FE}	typ.	150	270
		>	200	420
I_C = 2 mA; V_{CE} = 5 V	h_{FE}	typ.	290	520
		<	450	800

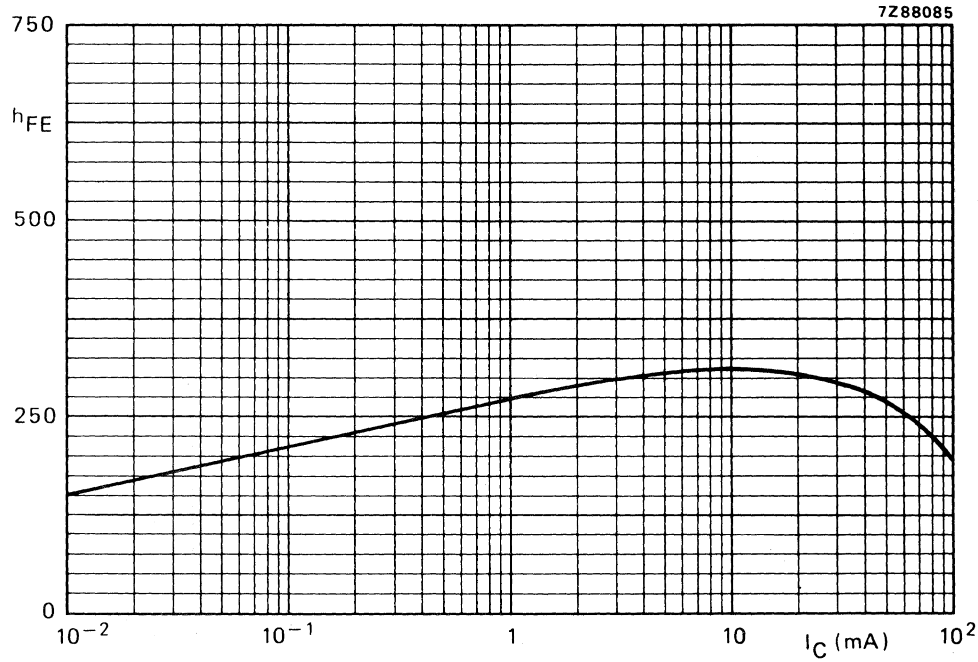


Fig. 3 Typical D.C. current gain B selections. V_{CE} = 5 V; T_j = 25 °C.

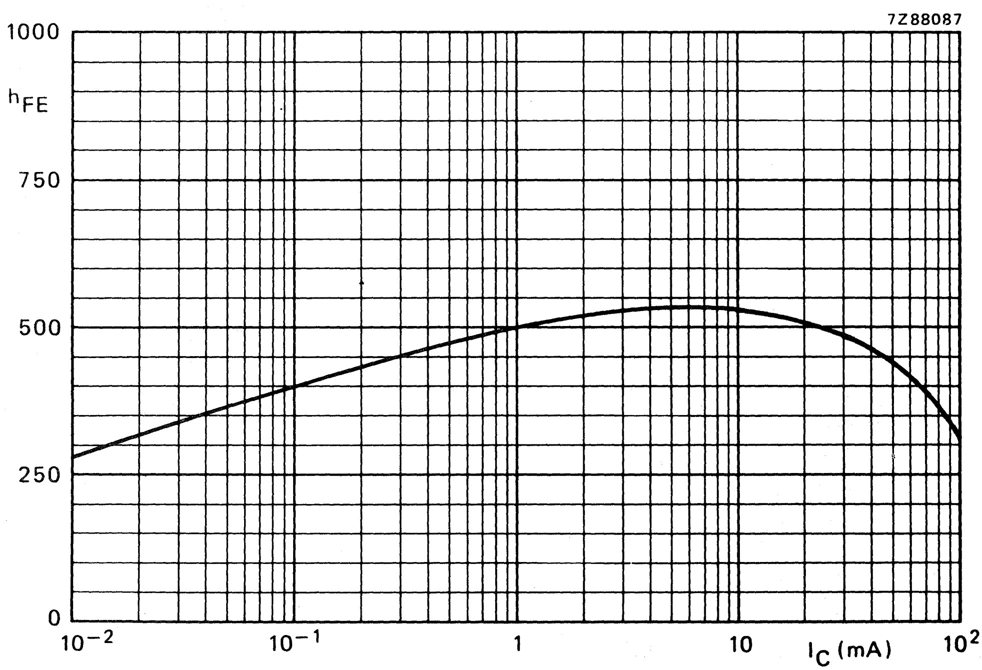


Fig. 4 Typical D.C. current gain C selections. V_{CE} = 5 V; T_j = 25 °C.

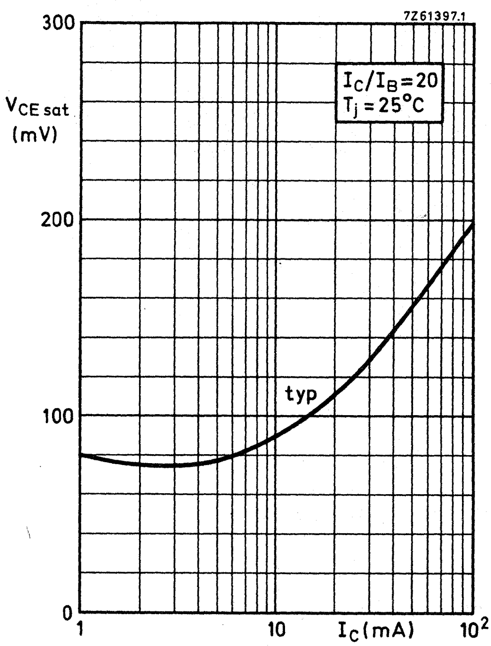


Fig. 5 Typical values.

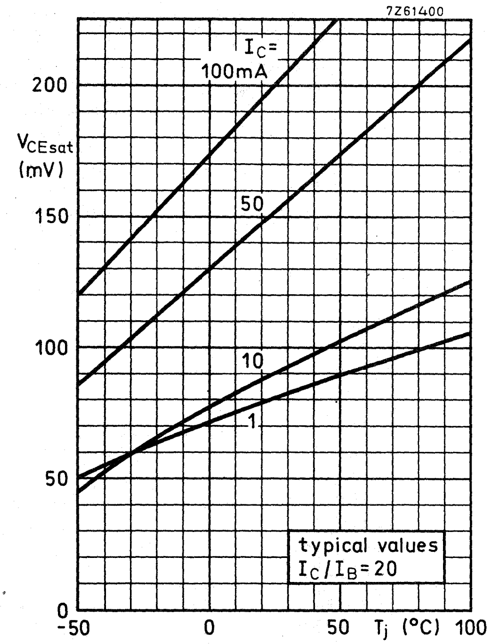


Fig. 6 Typical values; $I_C/I_B = 20$.

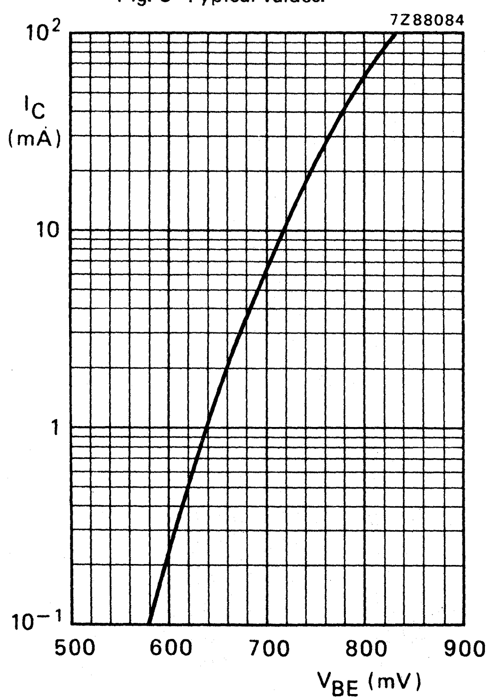


Fig. 7 Typical values V_{BE}. $V_{CE} = 5$ V; $T_j = 25\,^{o}C$.

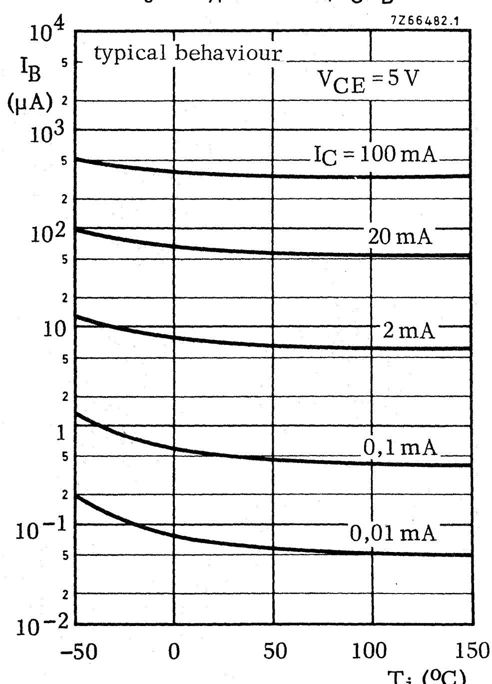


Fig. 8 Typical values.

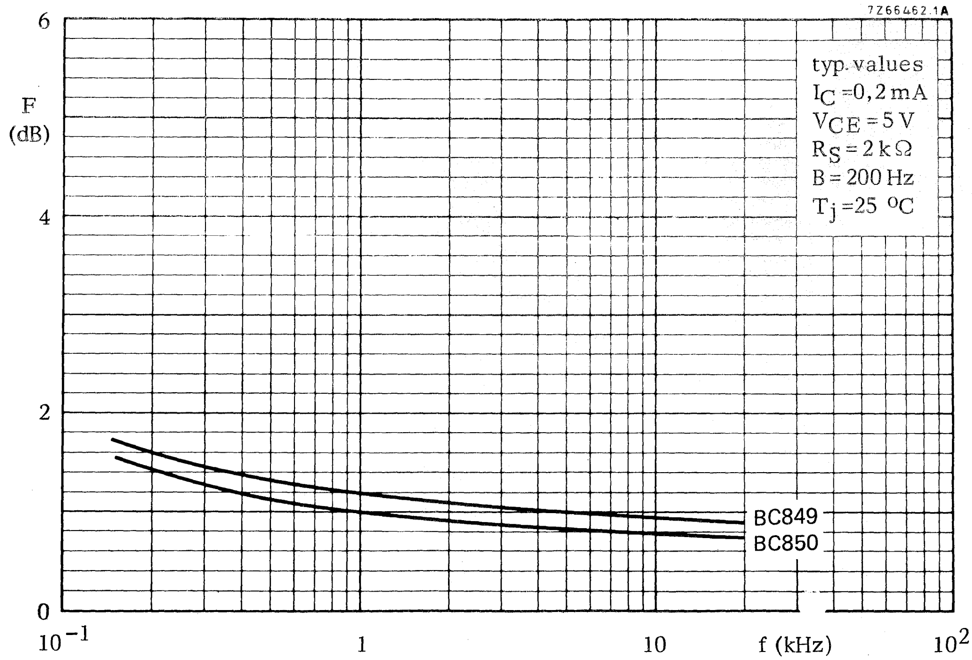

7Z66462.1A
typ. values
I_C = 0,2 mA
V_{CE} = 5 V
R_S = 2 kΩ
B = 200 Hz
T_j = 25 °C
F
(dB)
6
4
2
0
BC849
BC850
10^{-1}
1
10
f (kHz)
10^2

Fig. 9.

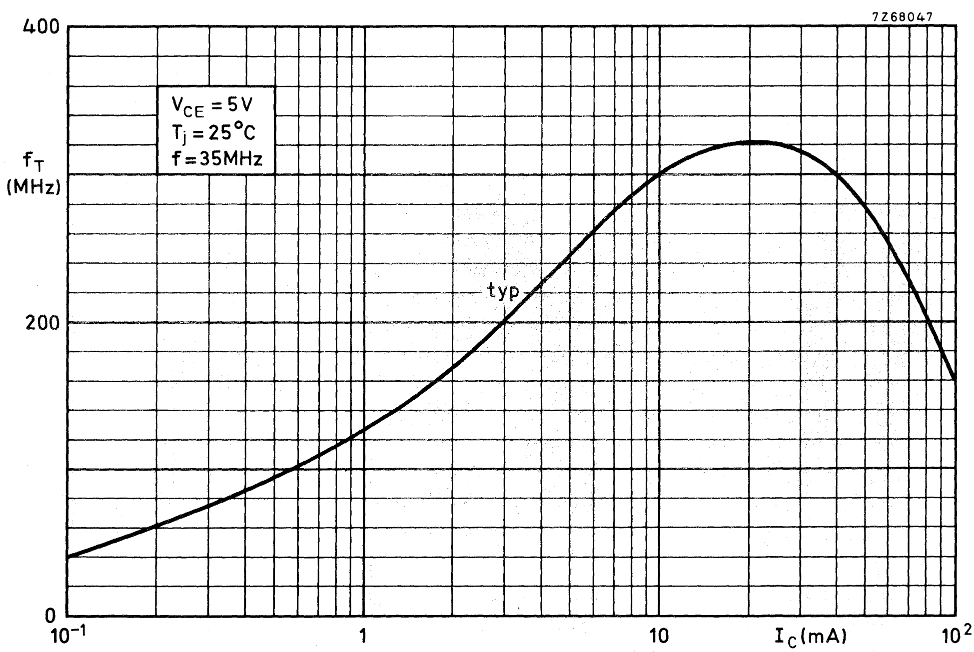

7Z68047
V_{CE} = 5 V
T_j = 25 °C
f = 35MHz
f_T
(MHz)
400
200
0
typ
10^{-1}
1
10
I_C (mA)
10^2

Fig. 10.

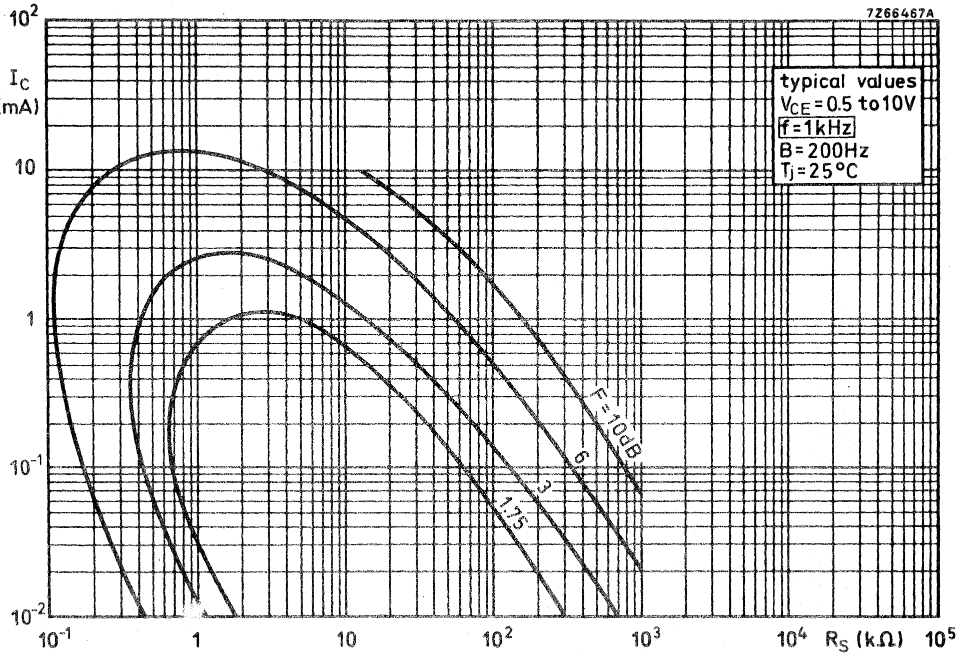


Fig. 11 Curves of constant noise figure for BC849.

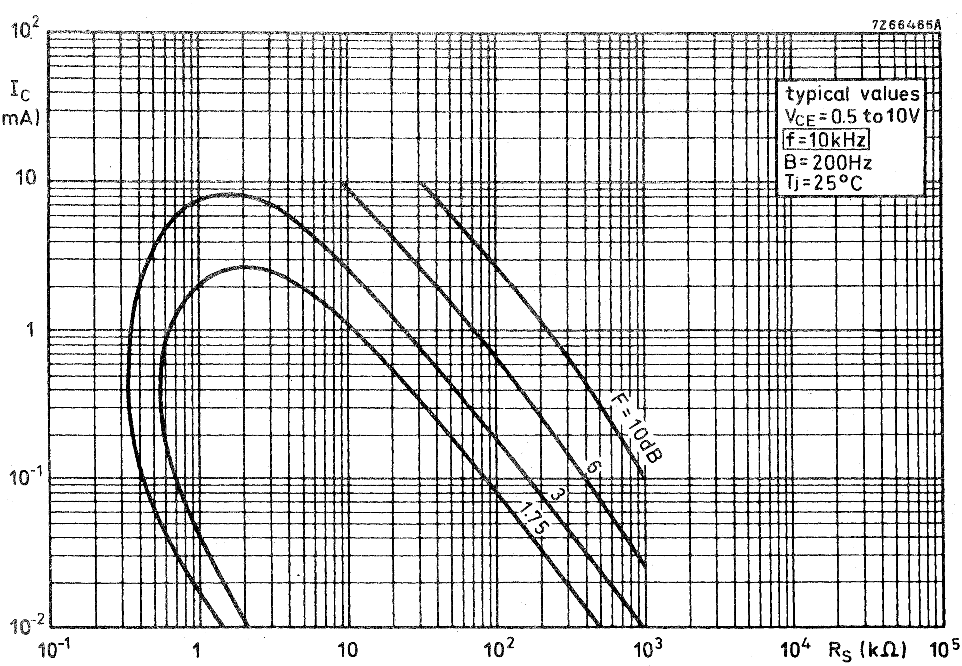


Fig. 12 Curves of constant noise figure for BC849.

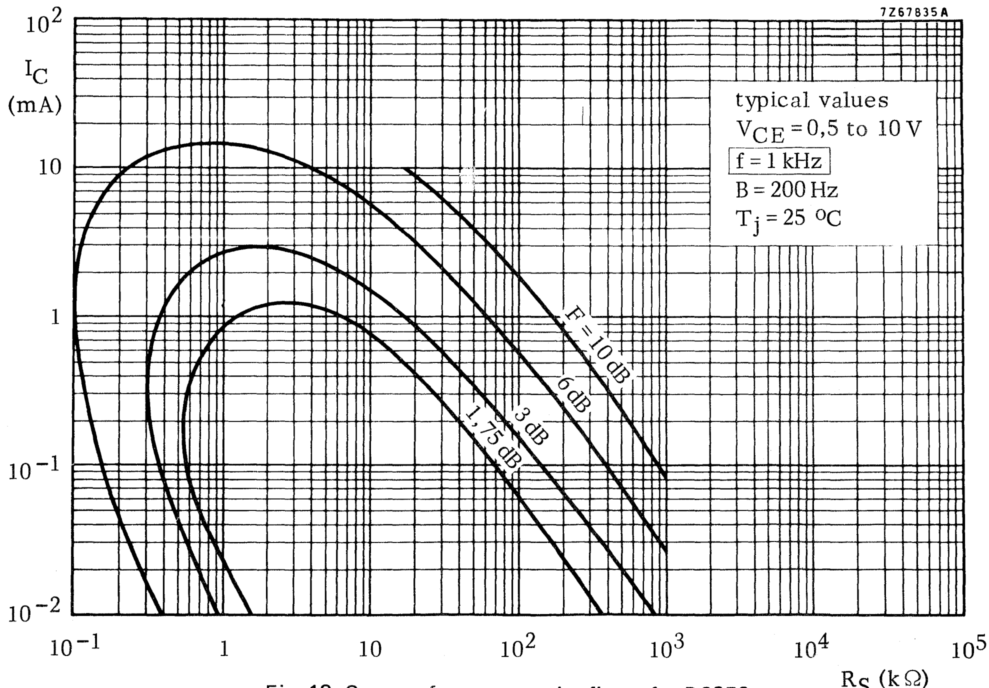


Fig. 13 Curves of constant noise figure for BC850.

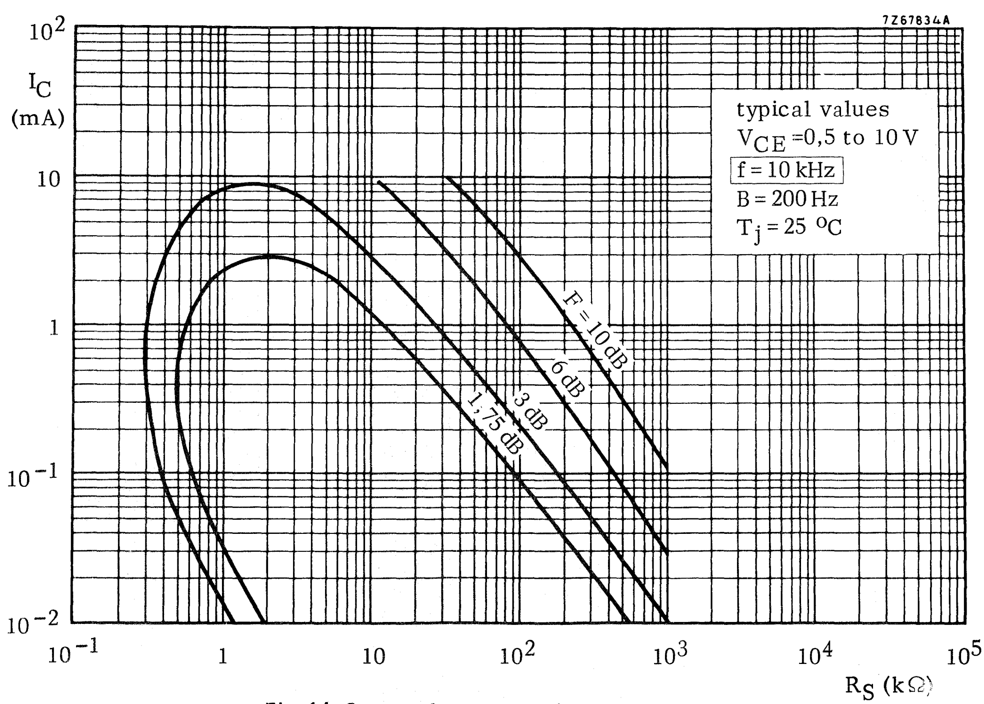


Fig. 14 Curves of constant noise figure for BC850.

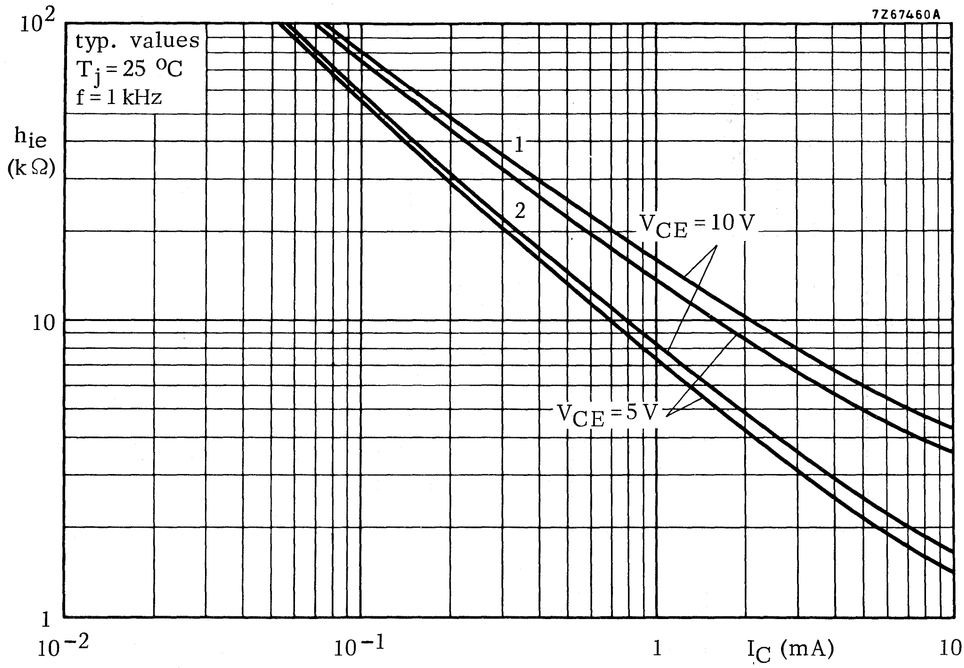


Fig. 15 Typical values. 1 = C selections; 2 = B selections.

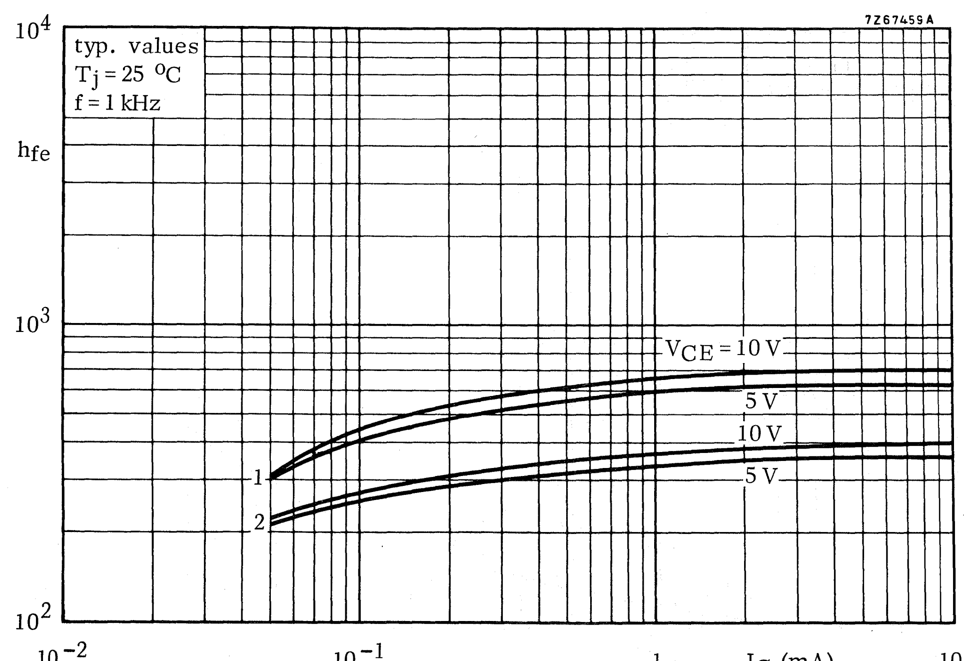


Fig. 16 Typical values. 1 = C selections; 2 = B selections.

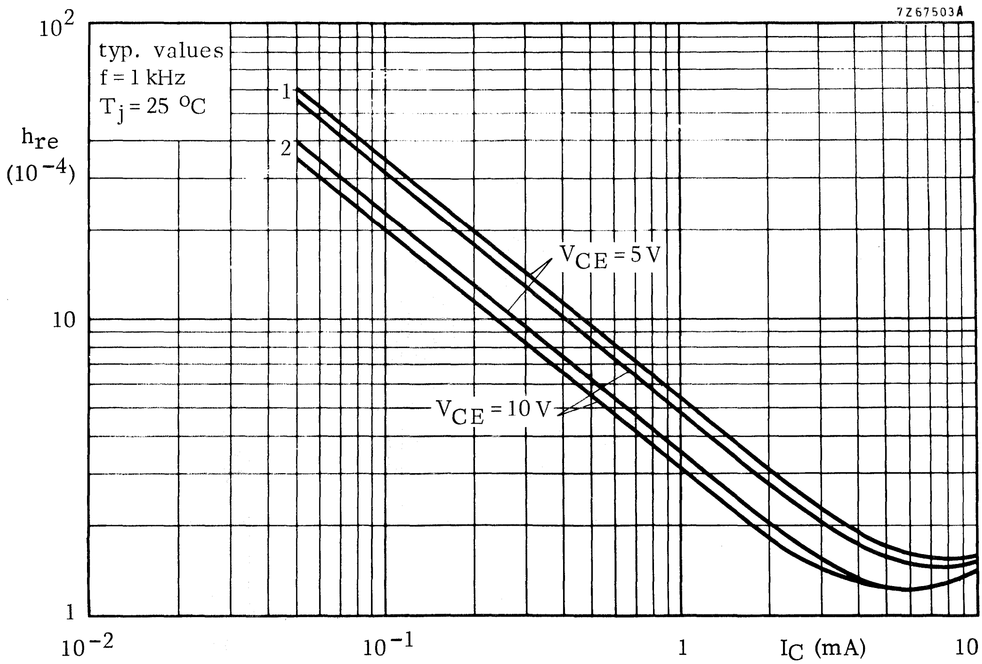


Fig. 17 Typical values. 1 = C selections; 2 = B selections.

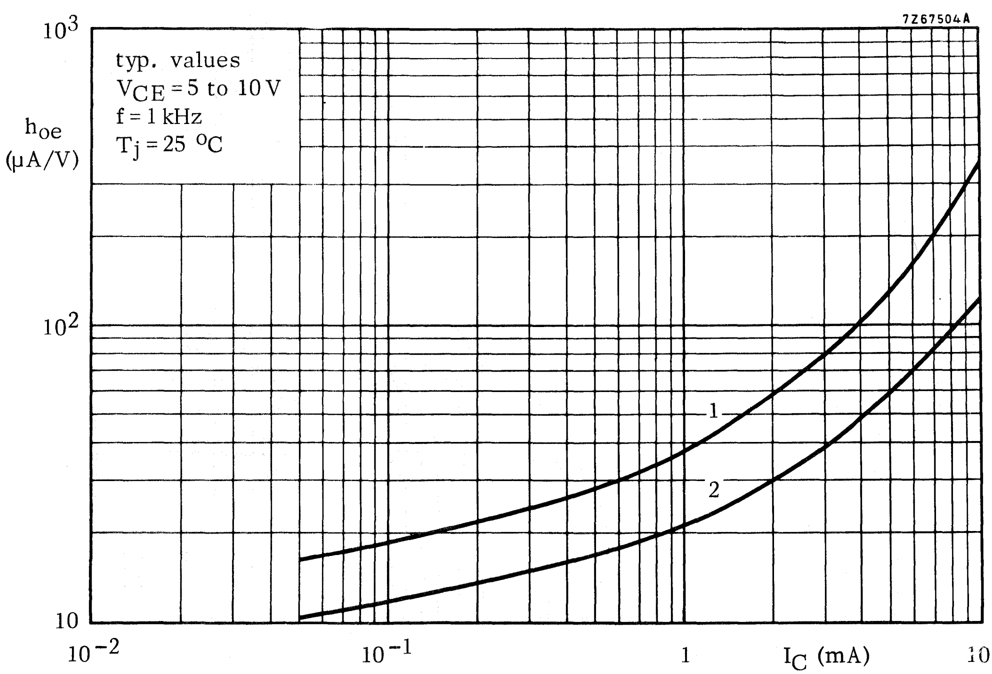


Fig. 18 Typical values. 1 = C selections; 2 = B selections.

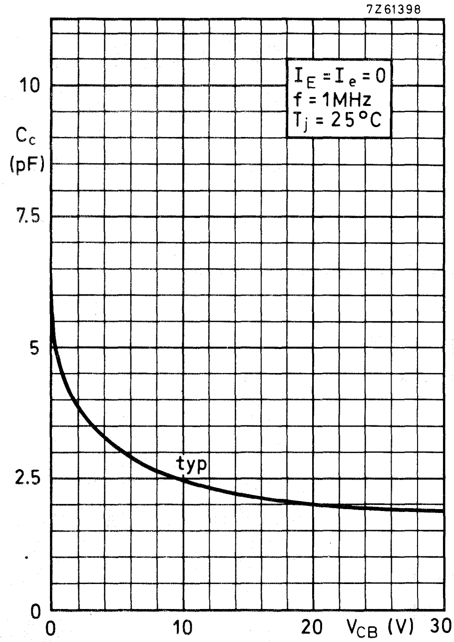


Fig. 19 Typical values.

SILICON PLANAR EPITAXIAL TRANSISTORS

P-N-P transistors, in a SOT-23 plastic envelope for use in driver and output stages of audio amplifiers in thick and thin-film circuits.

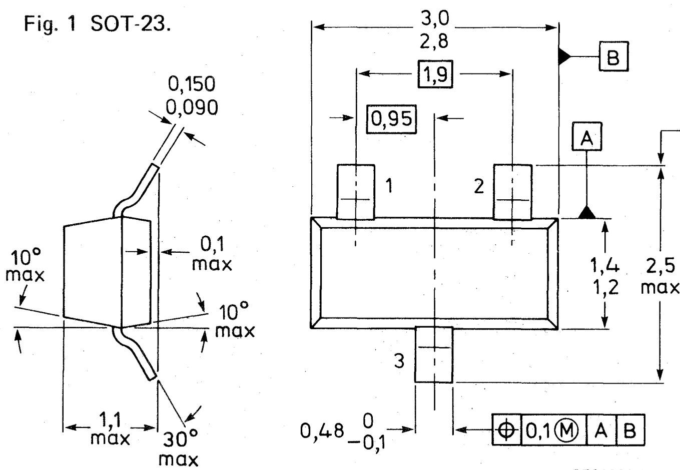
QUICK REFERENCE DATA

			BC856	BC857	BC858	
Collector-emitter voltage (+V_{BE} = 1 V)	$-V_{CEX}$	max.	80	50	30	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	65	45	30	V
Collector current (peak value)	$-I_{CM}$	max.		200		mA
Total power dissipation up to T_{amb} = 60 °C	P_{tot}	max.		200		mW
Junction temperature	T_j	max.		150		°C
Small-signal current gain $-I_C$ = 2 mA; $-V_{CE}$ = 5 V; f = 1 kHz	h_{fe}			75 to 900		
Transition frequency at f = 35 MHz $-I_C$ = 10 mA; $-V_{CE}$ = 5 V	f_T	typ.		150		MHz
Noise figure at R_S = 2 kΩ $-I_C$ = 200 μA; $-V_{CE}$ = 5 V f = 1 kHz; B = 200 Hz	F	<		10		dB

MECHANICAL DATA

Dimensions in mm

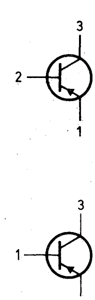
Fig. 1 SOT-23.



TOP VIEW

Marking code

BC856A = 3A
B = 3B
BC857A = 3E
B = 3F
C = 3G
BC858A = 3J
B = 3K
C = 3L



BC856AR = 3AR
BR = 3BR
BC857AR = 3ER
BR = 3FR
CR = 3GR
BC858AR = 3JR
BC = 3KR
CR = 3LR

R-types are available on request

See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BC856	BC857	BC858	
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	80	50	30	V
Collector-emitter voltage ($+V_{BE} = 1$ V)	$-V_{CEX}$	max.	80	50	30	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	65	45	30	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5	5	5	V

Collector current (d.c.)	$-I_C$	max.	100	mA
Collector current (peak value)	$-I_{CM}$	max.	200	mA
Emitter current (peak value)	I_{EM}	max.	200	mA
Base current (peak value)	$-I_{BM}$	max.	200	mA
Total power dissipation ** up to $T_{amb} = 60\ ^oC$	P_{tot}	max.	200	mW
Storage temperature	T_{stg}		−65 to + 150	^oC
Junction temperature	T_j	max.	150	^oC

THERMAL CHARACTERISTICS*

$T_j = Px\ (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	60	K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280	K/W
From soldering points to ambient**	$R_{th\ s\text{-}a}$	=	90	K/W

CHARACTERISTICS

$T_j = 25\ ^oC$ unless otherwise specified

Collector cut-off current				
$I_E = 0$; $-V_{CB} = 30$ V; T_j 25 ^oC	$-I_{CBO}$	typ.	1	nA
		<	15	nA
$T_j = 150\ ^oC$	$-I_{CBO}$	<	4	μA
Base-emitter voltage▲				
$-I_C = 2$ mA; $-V_{CE} = 5$ V	$-V_{BE}$	typ.	650	mV
			600 to 750	mV
$-I_C = 10$ mA; $-V_{CE} = 5$ V	$-V_{BE}$	<	820	mV

▲ $-V_{BE}$ decreases by about 2 mV/K with increasing temperature.
* See *Thermal characteristics.*
** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

Saturation voltages *

$-I_C$ = 10 mA; $-I_B$ = 0,5 mA	$-V_{CEsat}$	typ.	75 mV
		<	300 mV
	$-V_{BEsat}$	typ.	700 mV
$-I_C$ = 100 mA; $-I_B$ = 5 mA	$-V_{CEsat}$	typ.	250 mV
		<	650 mV
	$-V_{BEsat}$	typ.	850 mV

Knee voltage

$-I_C$ = 10 mA; $-I_B$ = value for which $-I_C$ = 11 mA at $-V_{CE}$ = 1 V	$-V_{CEK}$	typ.	250 mV
		<	600 mV

Collector capacitance at f = 1 MHz; $I_E = I_e = 0$; $-V_{CB}$ = 10 V		C_c	typ.	4,5 pF
Transition frequency at f = 35 MHz; $-I_C$ = 10 mA; $-V_{CE}$ = 5 V		f_T	typ.	150 MHz
Small-signal current gain at f = 1 kHz; $-I_C$ = 2 mA; $-V_{CE}$ = 5 V		h_{fe}		75 to 900
Noise figure at R_S = 2 kΩ; $-I_C$ = 200 μA; $-V_{CE}$ = 5 V; f = 1 kHz; B = 200 Hz		F	typ.	2 dB
			<	10 dB
D.C. current gain; $-I_C$ = 2 mA; $-V_{CE}$ = 5 V	BC856/857	h_{FE}		75 to 475
	BC858	h_{FE}		75 to 800
	BC856A/857A/858A	h_{FE}		125 to 250
	BC856B/857B/858B	h_{FE}		220 to 475
	BC857C/858C	h_{FE}		420 to 800

* $-V_{BEsat}$ decreases by about 1,7 mV/K with increasing temperature.

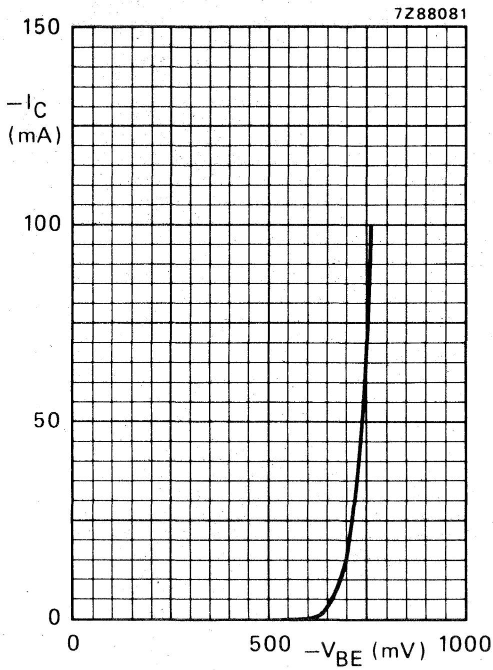


Fig. 3 Typical values. $-V_{CE}$ = 5 V; T_j = 25 °C.

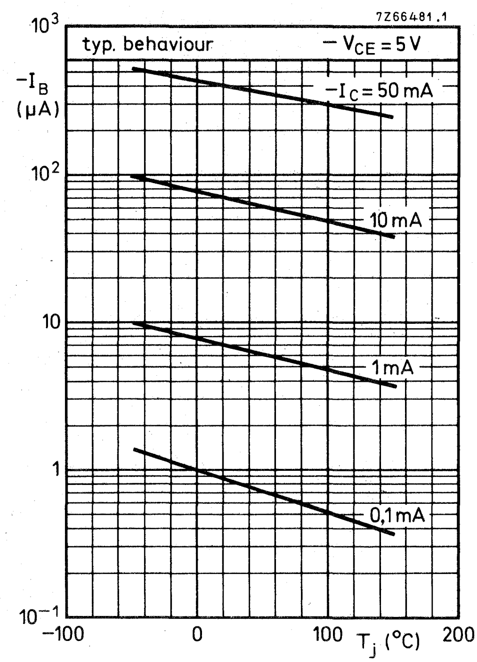


Fig. 4 Typical values.

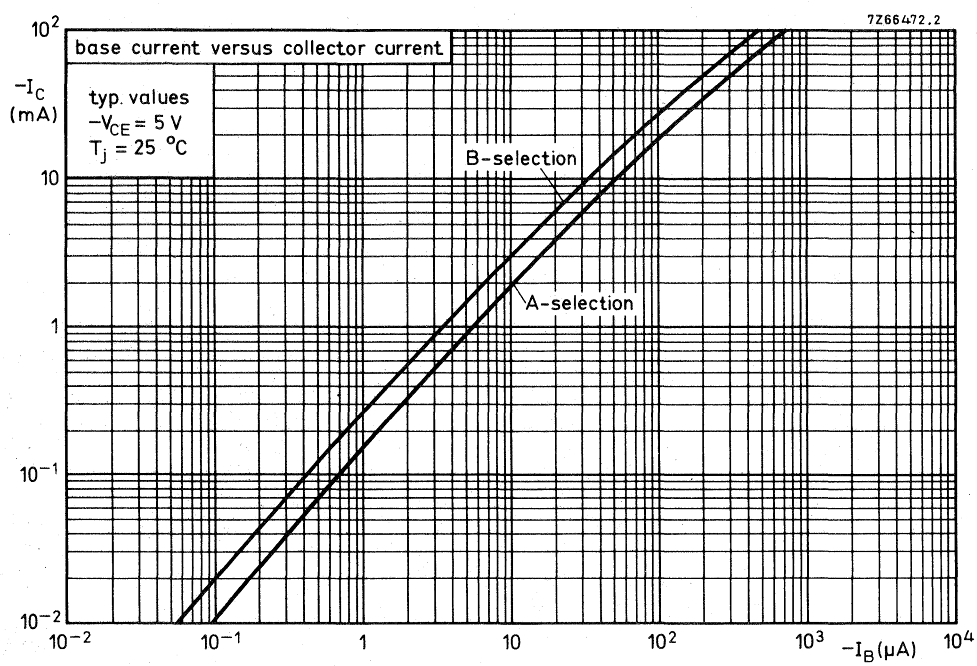


Fig. 5.

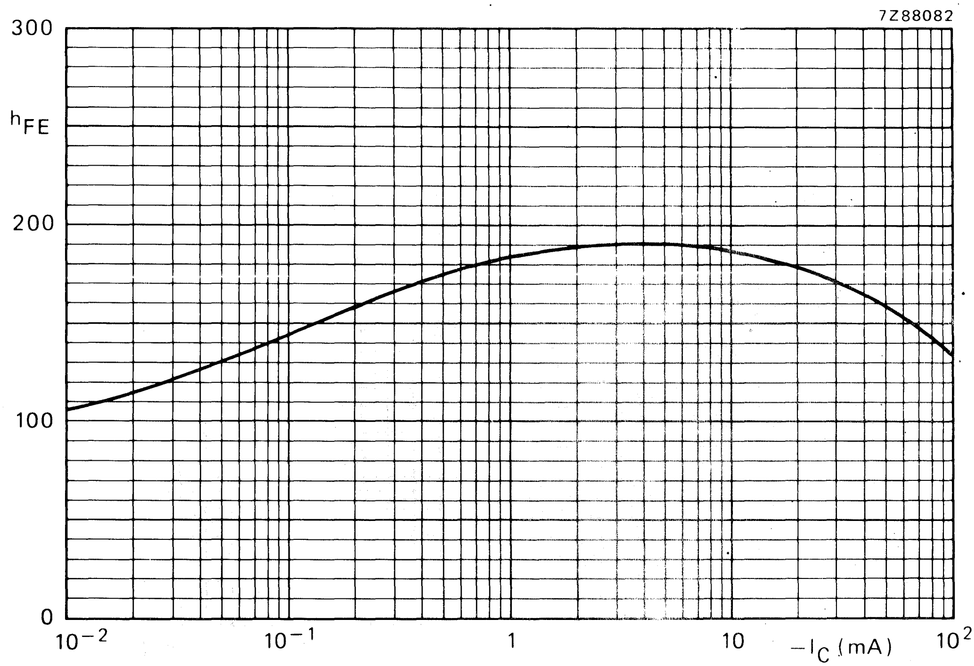


Fig. 6 Typical values D.C. current gain A-selections. $-V_{CE}$ = 5 V; T_j = 25 °C.

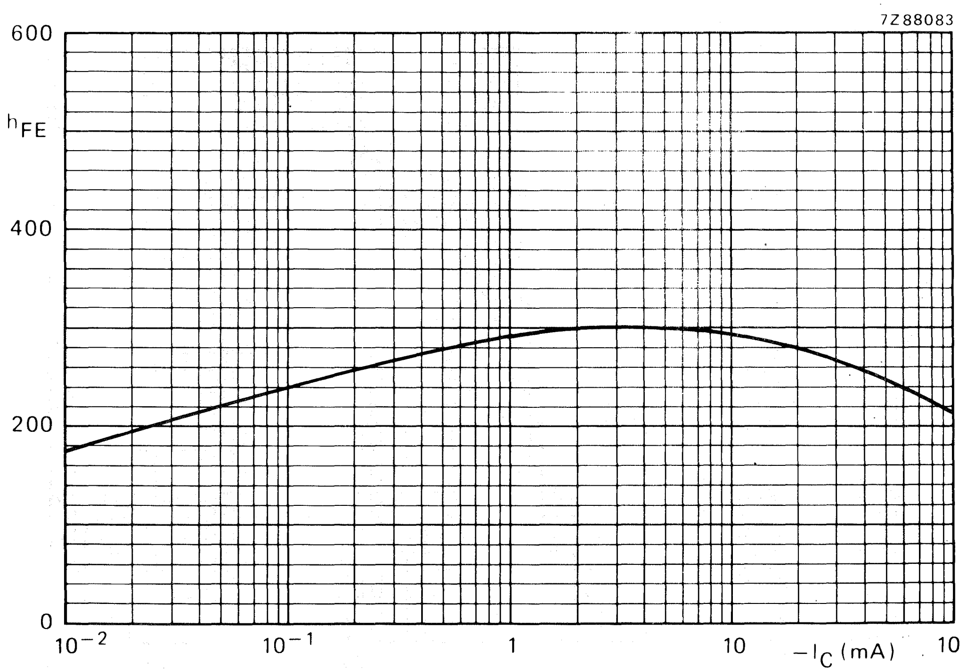


Fig. 7 Typical values D.C. current gain B-selections. $-V_{CE}$ = 5 V; T_j = 25 °C.

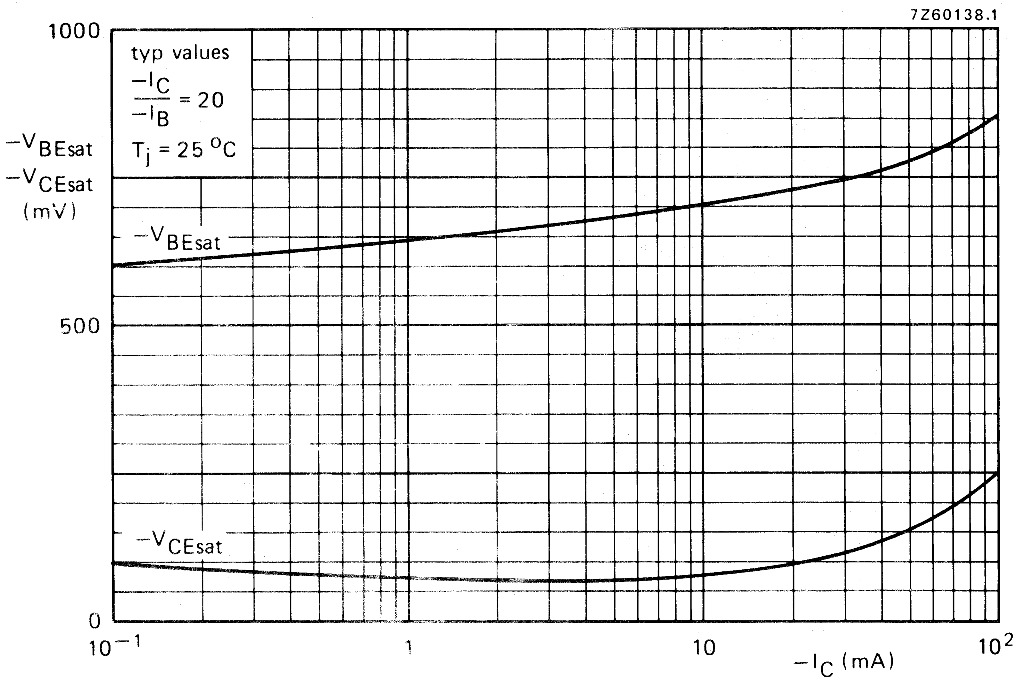


Fig. 8 Typical values base-emitter and collector-emitter saturation voltage.

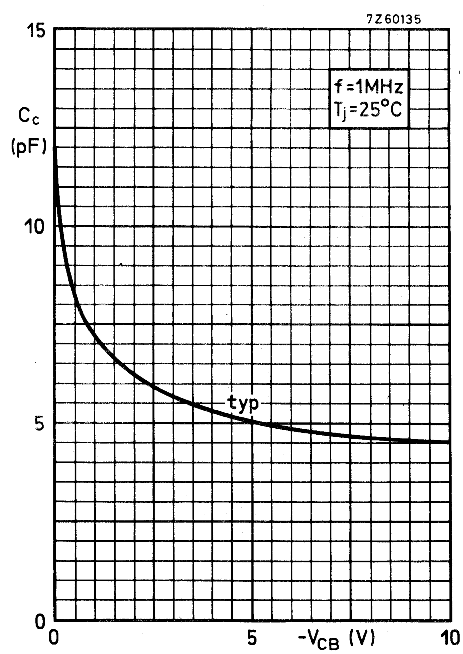


Fig. 9 Typical values.

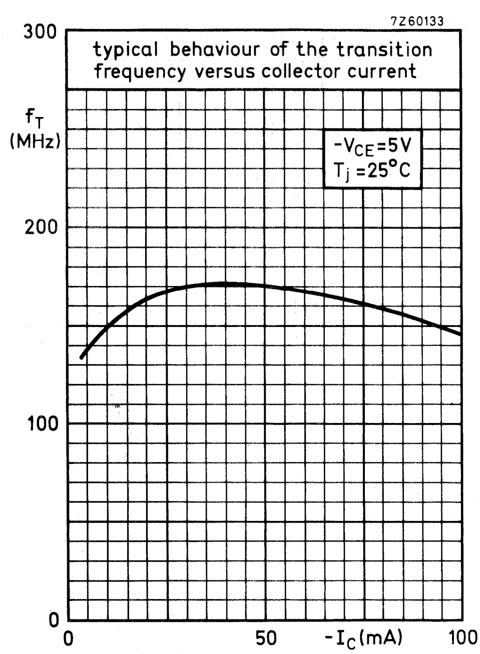


Fig. 10 Typical values. f = 35 MHz.

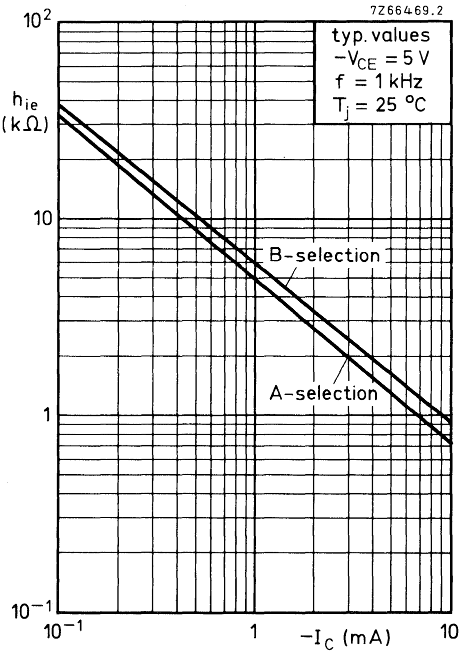


Fig. 11.

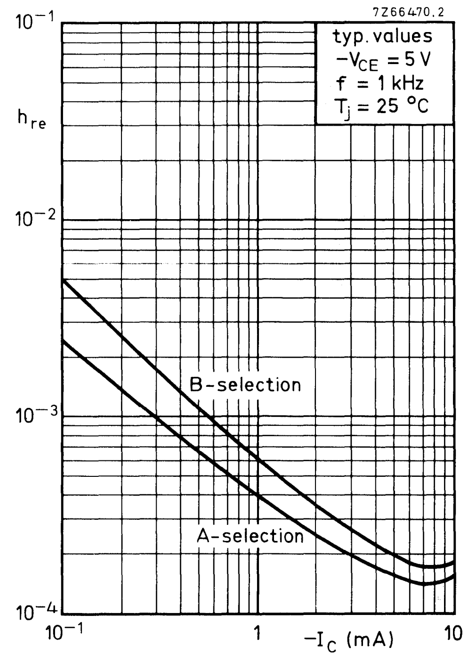


Fig. 12.

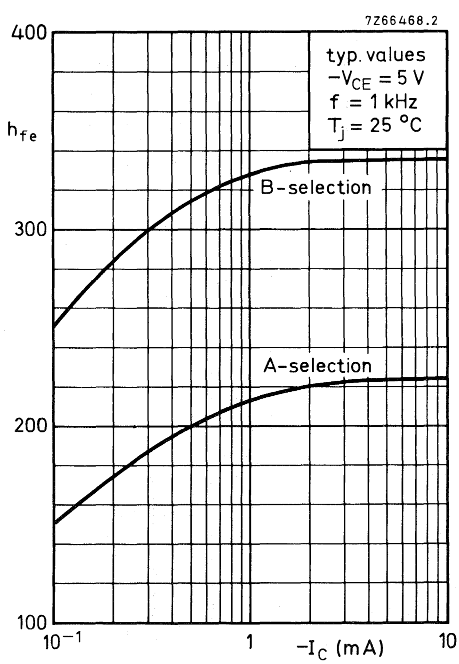


Fig. 13.

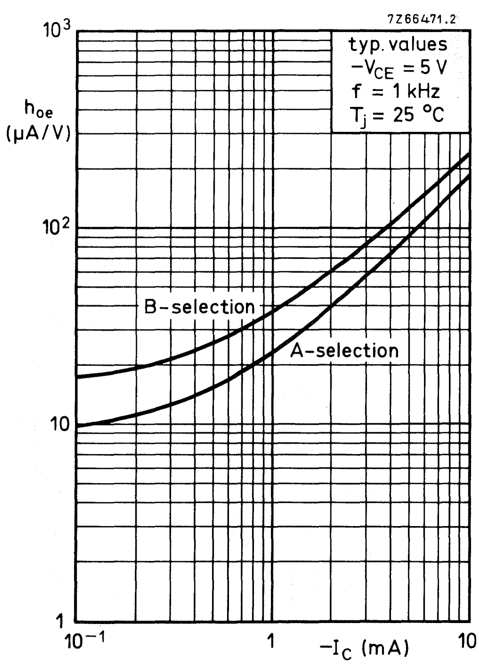


Fig. 14.

SILICON PLANAR EPITAXIAL TRANSISTORS

P-N-P transistors in a plastic SOT-23 envelope, primarily intended for low-noise input stages in tape recorders, hi-fi amplifiers and other audio frequency equipment in thick and thin-film hybrid circuits.

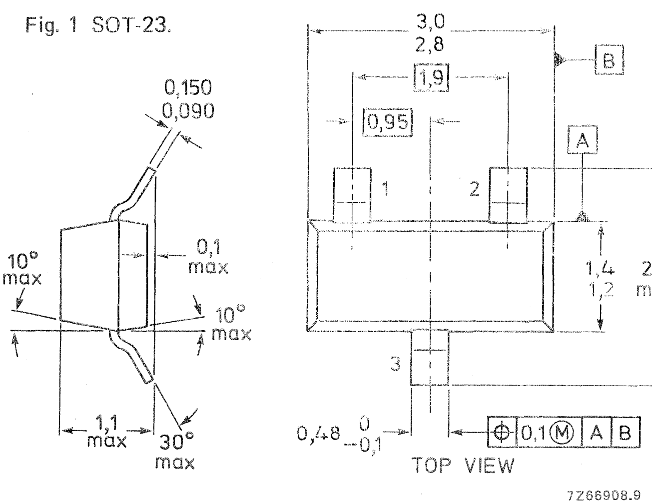
QUICK REFERENCE DATA

			BC859	BC860	
Collector-emitter voltage ($+V_{BE} = 1$ V)	$-V_{CEX}$	max.	30	50	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	30	45	V
Collector current (peak value)	$-I_{CM}$	max.	200	200	mA
Total power dissipation up to $T_{amb} = 60$ °C	P_{tot}	max.	200	200	mW
Junction temperature	T_j	max.	150	150	°C
Small-signal current gain $-I_C = 2$ mA; $-V_{CE} = 5$ V; f = 1 kHz	h_{fe}	>	125	125	
		<	900	900	
Transition frequency $-I_C = 10$ mA; $-V_{CE} = 5$ V	f_T	typ.	150	150	MHz
Noise figure at $R_s = 2$ kΩ; $-I_C = 200$ μA; $-V_{CE} = 5$ V; f = 30 Hz to 15 kHz	F	typ.	1,2	1	dB
		<	4	3	dB
f = 1 kHz; B = 200 Hz	F	<	4	4	dB

MECHANICAL DATA

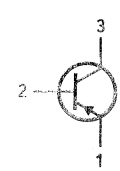
Dimensions in mm

Fig. 1 SOT-23.

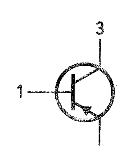


Marking code

BC859A = 4A
B = 4B
C = 4C
BC860A = 4E
B = 4F
C = 4G



BC859AR = 4AR
BR = 4BR
CR = 4CR
BC860AR = 4ER
BR = 4FR
CR = 4GR



R-types are available on request

See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BC859	BC860	
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	30	50	V
Collector-emitter voltage (+ V_{BE} = 1 V)	$-V_{CEX}$	max.	30	50	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	30	45	V
Emitter-base voltage (open collector)	$-V_{CBO}$	max.	5	5	V
Collector current (d.c.)	$-I_C$	max.	100		mA
Collector current (peak value)	$-I_{CM}$	max.	200		mA
Emitter current (peak value)	I_{EM}	max.	200		mA
Base current (peak value)	$-I_{BM}$	max.	200		mA
Total power dissipation up to T_{amb} = 60 °C**	P_{tot}	max.	200		mW
Storage temperature	T_{stg}		−65 to + 150		°C
Junction temperature	T_j	max.	150		°C

THERMAL CHARACTERISTICS*

$T_j = P \times (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	60	K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280	K/W
From soldering points to ambient**	$R_{th\ s\text{-}a}$	=	90	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current

$I_E = 0$; $-V_{CB}$ = 30 V; T_j = 25 °C	$-I_{CBO}$	typ.	1	nA
		<	15	nA
T_j = 150 °C	$-I_{CBO}$	<	4	μA

Base-emitter voltage ▲

$-I_C$ = 2 mA; $-V_{CE}$ = 5 V	$-V_{BE}$	typ.	650	mV
			600 to 750	mV
$-I_C$ = 10 mA; $-V_{CE}$ = 5 V	$-V_{BE}$	<	820	mV

* See *Thermal characteristics.*
** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.
▲ $-V_{BE}$ decreases by about 2 mV/K with increasing temperature.

Saturation voltages*				
$-I_C$ = 10 mA; $-I_B$ = 0,5 mA	$-V_{CEsat}$	typ.	75	mV
		<	300	mV
	$-V_{BEsat}$	typ.	700	mV
$-I_C$ = 100 mA; $-I_B$ = 5 mA	$-V_{CEsat}$	typ.	250	mV
		<	650	mV
	$-V_{BEsat}$	typ.	850	mV
Collector capacitance at f = 1 MHz				
$I_E = I_e = 0$; $-V_{CB}$ = 10 V	C_c	typ.	4,5	pF
Transition frequency at f = 35 MHz				
$-I_C$ = 10 mA; $-V_{CE}$ = 5 V	f_T	typ.	150	MHz
Small-signal current gain at f = 1 kHz				
$-I_C$ = 2 mA; $-V_{CE}$ = 5 V	h_{fe}		125 to 900	

Noise figure at R_S = 2 kΩ					
$-I_C$ = 200 μA; $-V_{CE}$ = 5 V			BC859	BC860	
f = 30 Hz to 15 kHz	F	typ.	1,2	1	dB
		<	4	3	dB
f = 1 kHz; B = 200 Hz	F	typ.	1	1	dB
		<	4	4	dB
Equivalent noise voltage at R_S = 2 kΩ					
$-I_C$ = 200 μA; $-V_{CE}$ = 5 V f = 10 Hz to 50 Hz; T_{amb} = 25 °C	V_n	<	–	0,11	μV

D.C. current gain		
$-I_C$ = 2 mA; $-V_{CE}$ = 5 V; total range	h_{FE}	125 to 800
A selections	h_{FE}	125 to 250
B selections	h_{FE}	220 to 475
C selections	h_{FE}	420 to 800

* $-V_{BEsat}$ decreases by about 1,7 mV/K with increasing temperature.

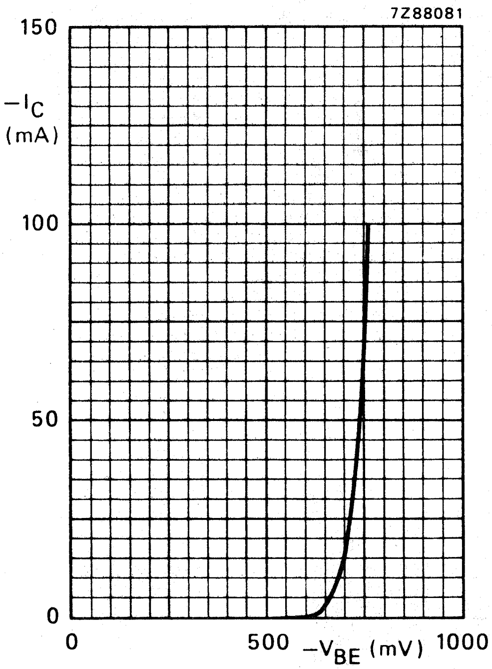


Fig. 3 Typical values. $-V_{CE} = 5$ V; $T_j = 25$ °C.

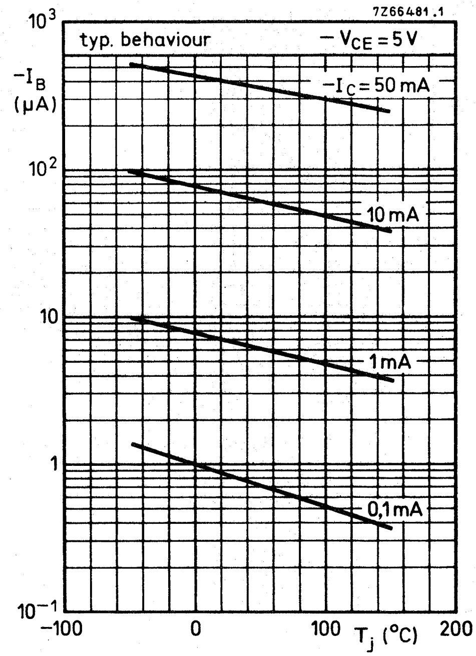


Fig. 4 Typical values.

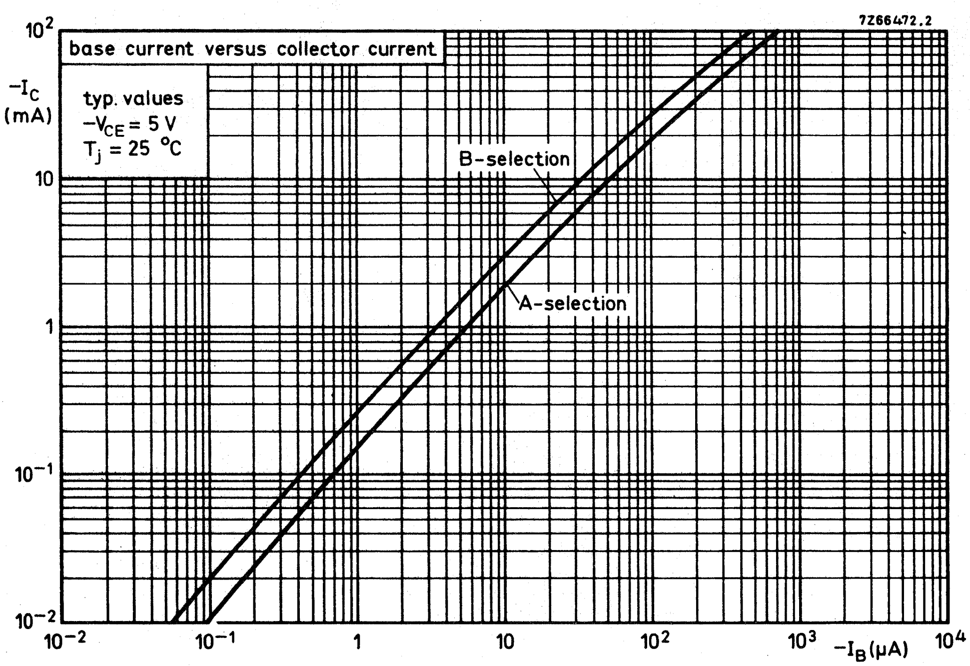


Fig. 5.

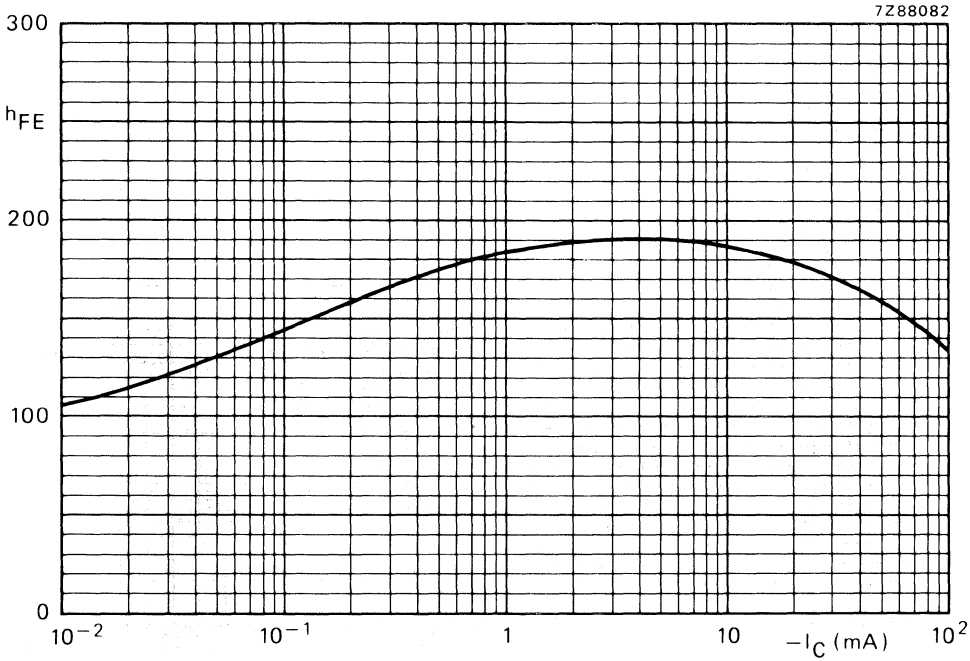


Fig. 6 Typical values. D.C. current gain A-selections. $-V_{CE}$ = 5 V; T_j = 25 °C.

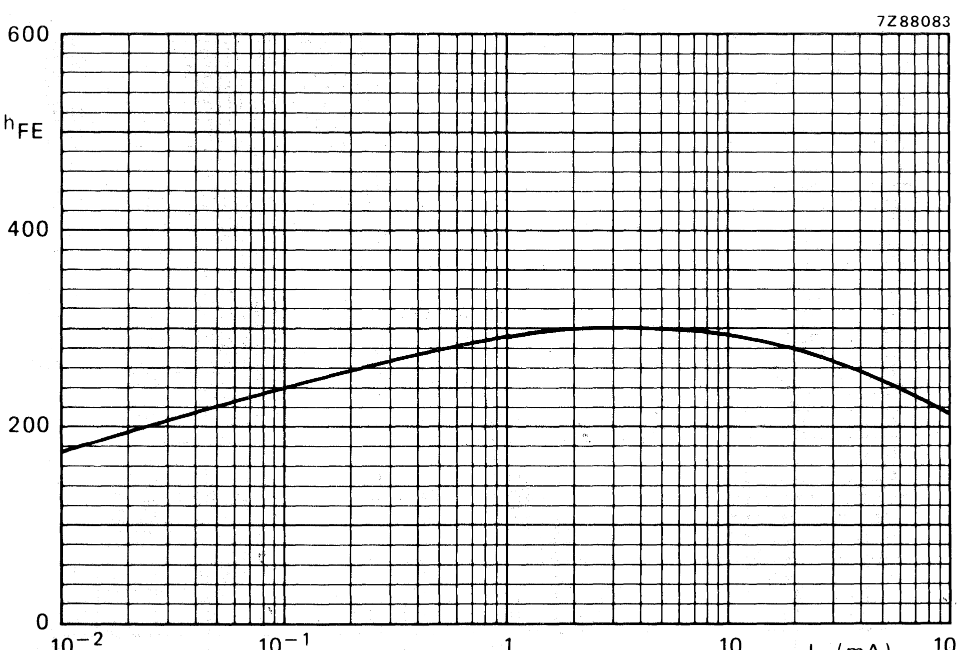


Fig. 7 Typical values. D.C. current gain B-selections. $-V_{CE}$ = 5 V; T_j = 25 °C.

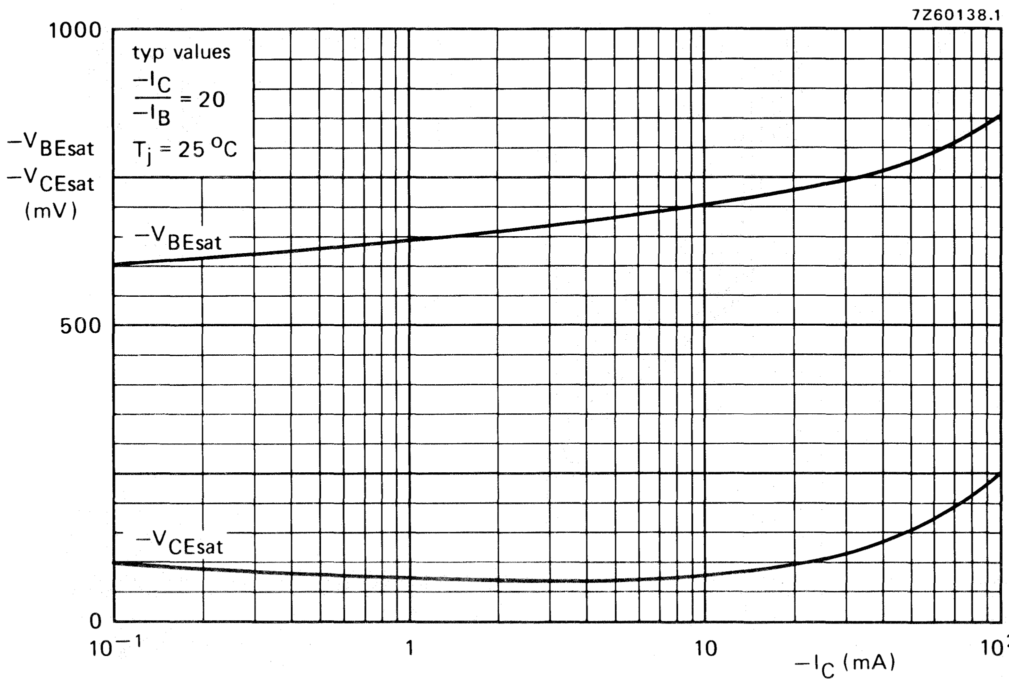


Fig. 8 Typical values base-emitter and collector-emitter saturation voltage.

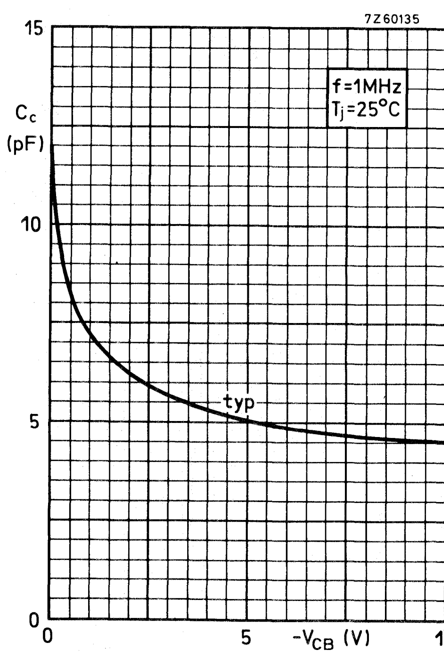


Fig. 9 Typical values.

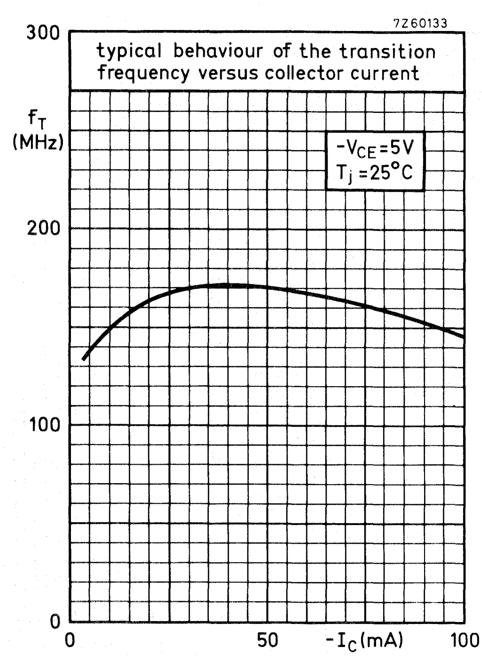


Fig. 10 Typical values. f = 35 MHz.

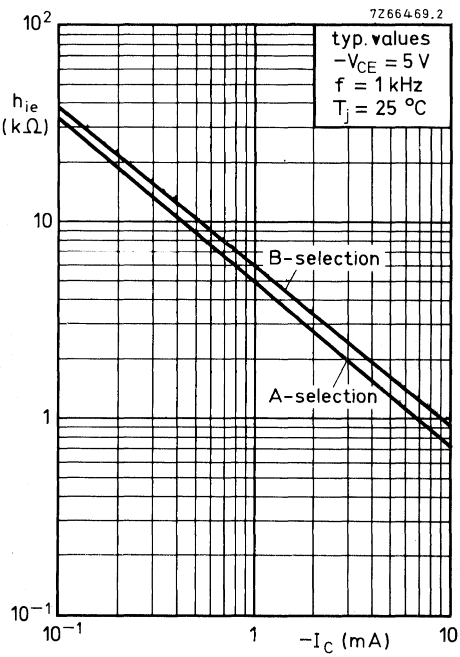


Fig. 11 Typical values.

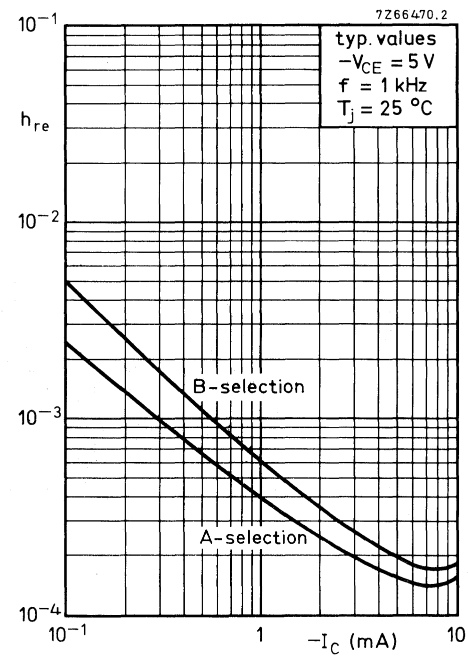


Fig. 12 Typical values.

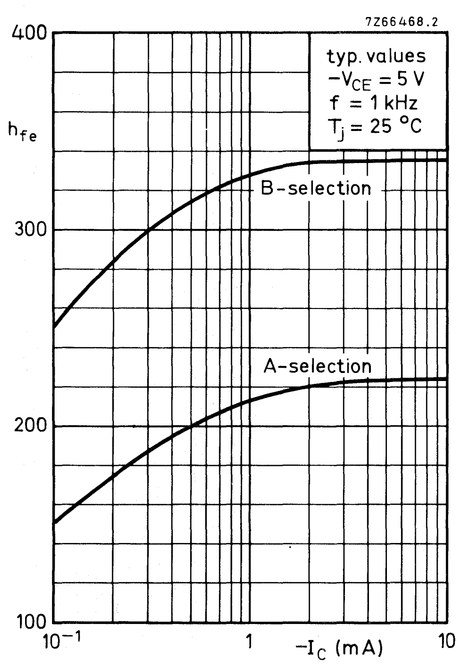


Fig. 13 Typical values.

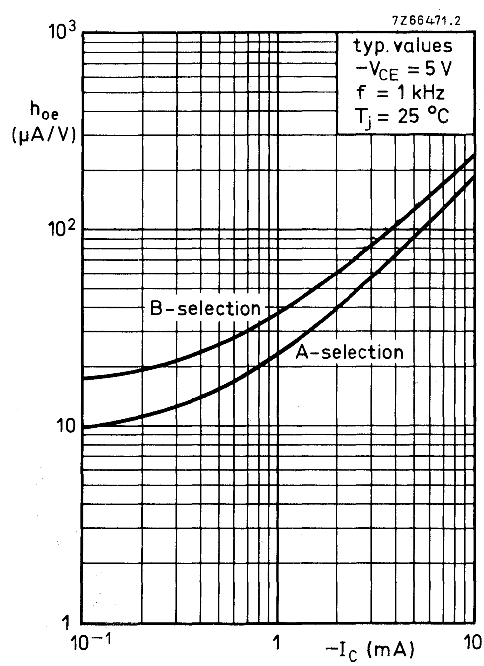


Fig. 14 Typical values.

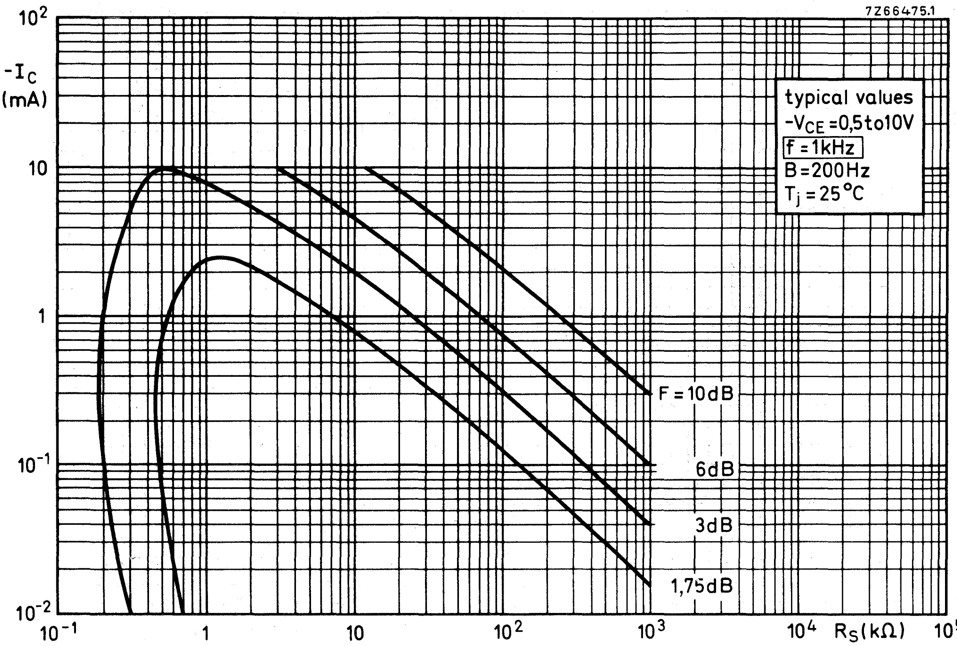


Fig. 15 Curves of constant noise figure at f = 1 kHz.

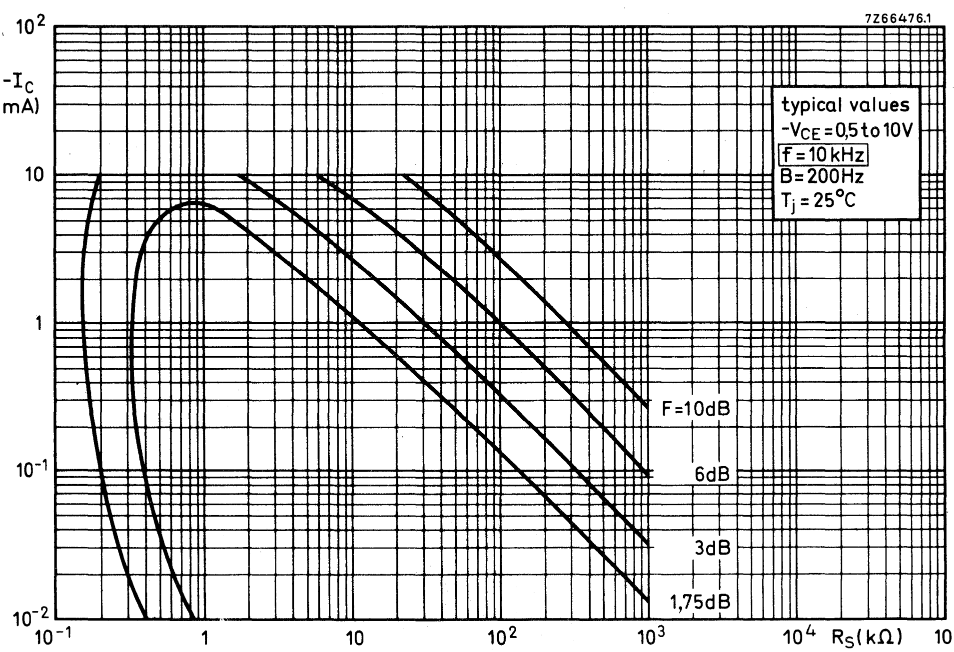


Fig. 16 Curves of constant noise figure at f = 10 kHz.

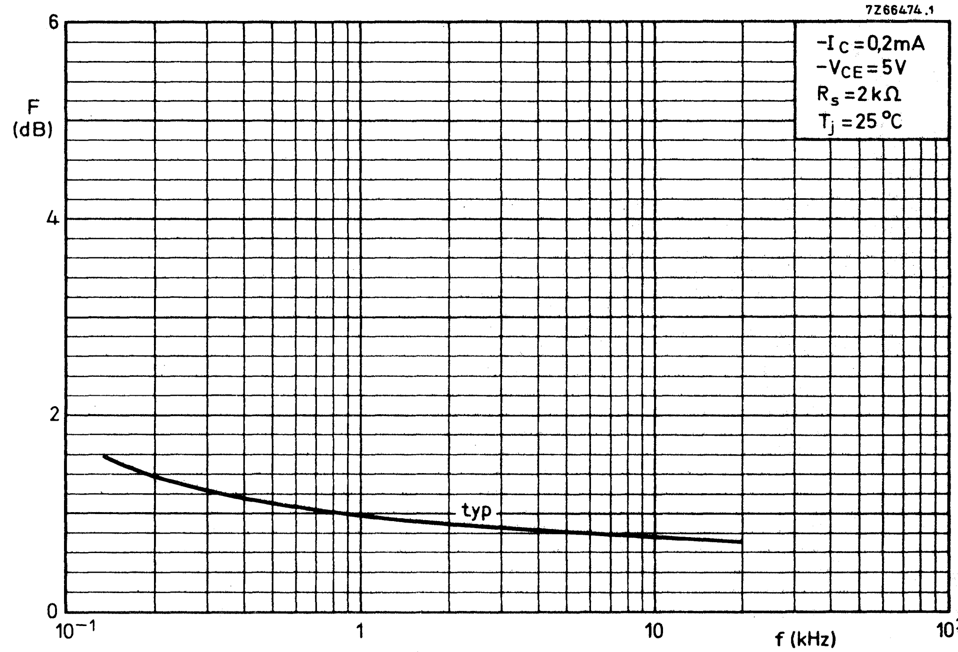


Fig. 17 Typical values noise figure.

SILICON PLANAR EPITAXIAL TRANSISTOR

N-P-N transistor in a microminiature plastic envelope intended for low-voltage, high-current l.f. applications. BC868/BC869 is the matched complementary pair suitable for class-B audio output stages up to 3 W.

QUICK REFERENCE DATA

Collector-emitter voltage ($V_{BE} = 0$)	V_{CES}	max.	25	V
Collector-emitter voltage (open base)	V_{CEO}	max.	20	V
Collector current (peak value)	I_{CM}	max.	2	A
Total power dissipation up to $T_{amb} = 25\ ^oC$	P_{tot}	max.	1	W
Junction temperature	T_j	max.	150	^oC
D.C. current gain $I_C = 500$ mA; $V_{CE} = 1$ V	h_{FE}		85 to 375	
Transition frequency at f = 35 MHz $I_C = 10$ mA; $V_{CE} = 5$ V	f_T	typ.	60	MHz

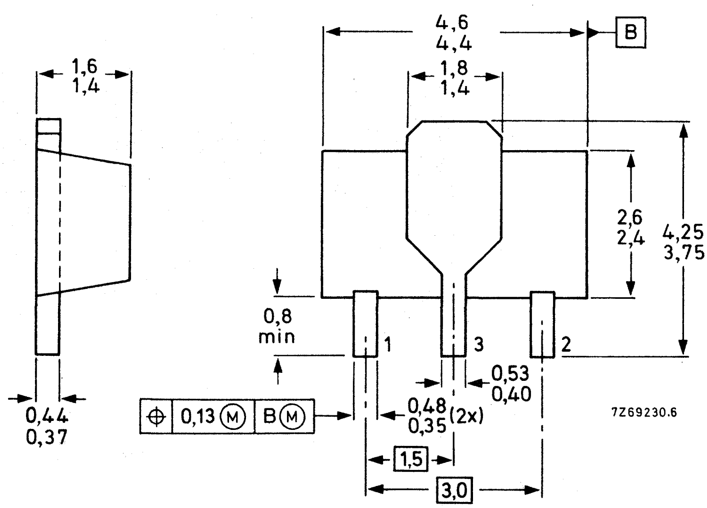
MECHANICAL DATA

Dimensions in mm

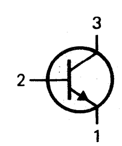
Mark

Fig. 1 SOT-89.

CAC



BOTTOM VIEW



See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-emitter voltage (V_{BE} = 0)	V_{CES}	max.	25	V
Collector-emitter voltage (open base)	V_{CEO}	max.	20	V
Emitter-base voltage (open collector)	V_{EBO}	max.	5	V
Collector current (d.c.)	I_C	max.	1	A
Collector current (peak value)	I_{CM}	max.	2	A
Base current (d.c.)	I_B	max.	100	mA
Base current (peak value)	I_{BM}	max.	200	mA
Total power dissipation up to T_{amb} = 25 °C*	P_{tot}	max.	1	W
Storage temperature	T_{stg}	−65 to + 150		°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE

From junction to ambient in free air*	$R_{th\ j\text{-}a}$	=	125	K/W
From junction to tab	$R_{th\ j\text{-}t}$	=	10	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current				
I_E = 0; V_{CB} = 25 V	I_{CBO}	<	10	μA
I_E = 0; V_{CB} = 25 V; T_j = 150 °C	I_{CBO}	<	1	mA
Emitter cut-off current				
I_C = 0; V_{EB} = 5 V	I_{EBO}	<	10	μA
Base-emitter voltage				
I_C = 5 mA; V_{CE} = 10 V	V_{BE}	typ.	0,62	V
I_C = 1 A; V_{CE} = 1 V	V_{BE}	<	1	V
Collector-emitter saturation voltage				
I_C = 1 A; I_B = 100 mA	V_{CEsat}	<	0,5	V
D.C. current gain				
I_C = 5 mA; V_{CE} = 10 V	h_{FE}	>	50	
I_C = 500 mA; V_{CE} = 1 V	h_{FE}	85 to 375		
I_C = 1 A; V_{CE} = 1 V	h_{FE}	>	60	
Collector capacitance at f = 450 kHz				
$I_E = I_e$ = 0; V_{CB} = 5 V	C_c	typ.	27	pF
Transition frequency at f = 35 MHz				
I_C = 10 mA; V_{CE} = 5 V	f_T	typ.	60	MHz

* Mounted on a ceramic substrate, area = 2,5 cm^2; thickness = 0,7 mm.

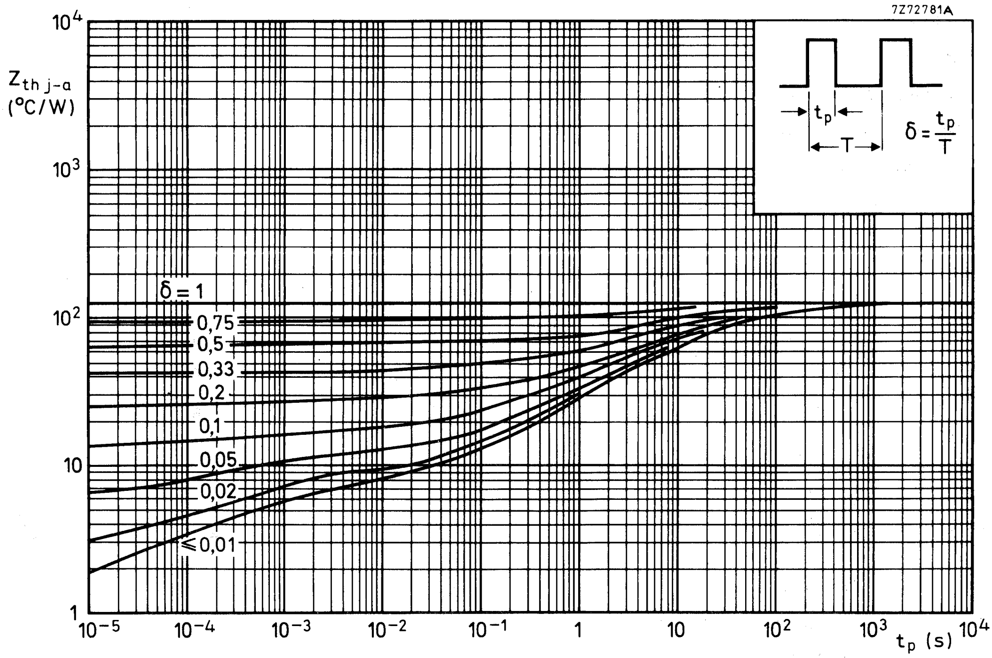


Fig. 2 Pulse power rating chart.

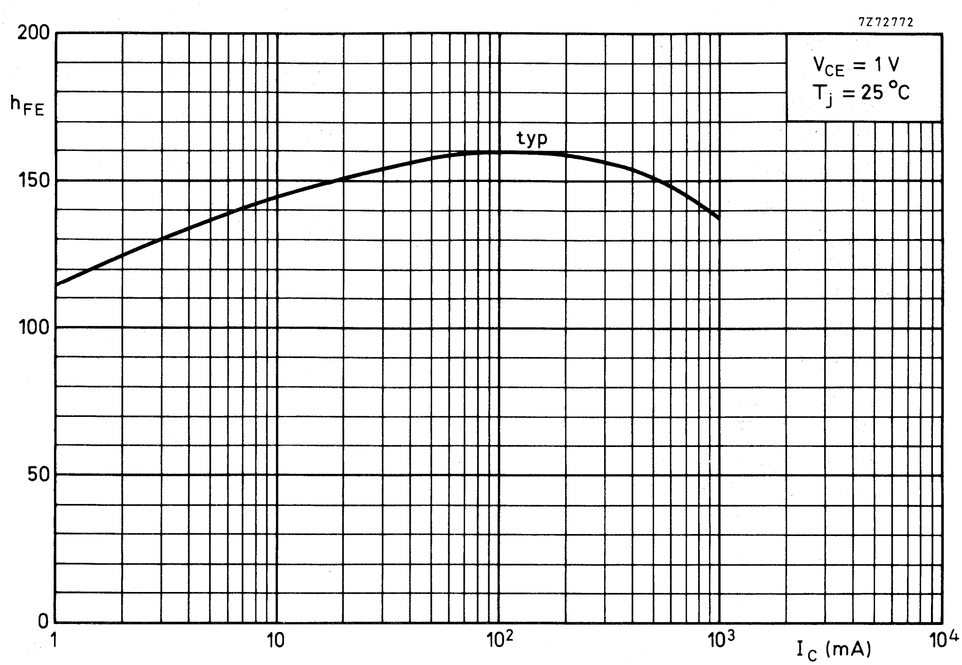


Fig. 3 D.C. current gain.

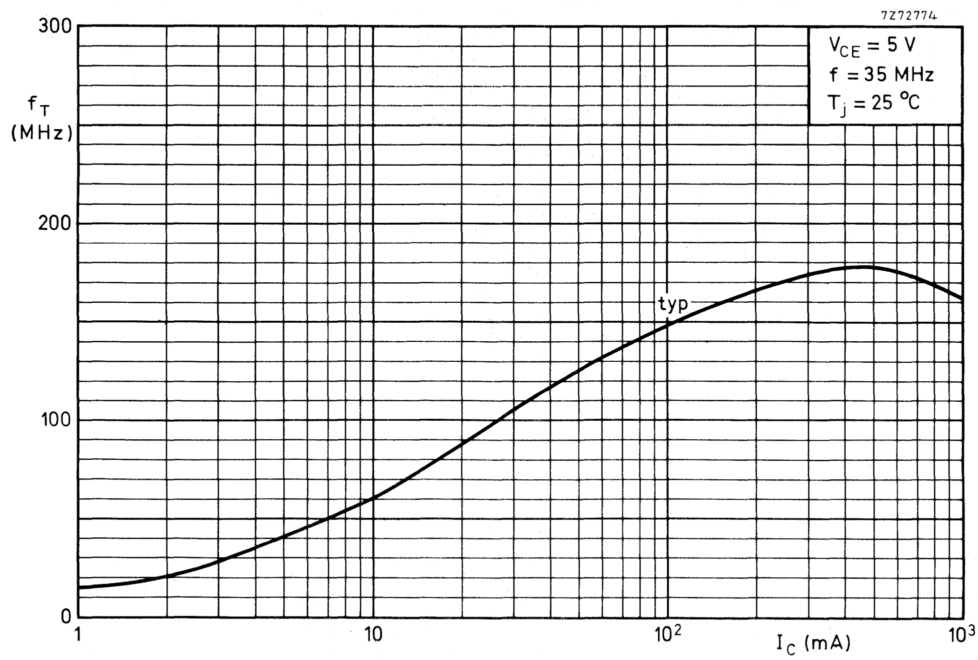


Fig. 4 Typical values transition frequency as a function of collector current.

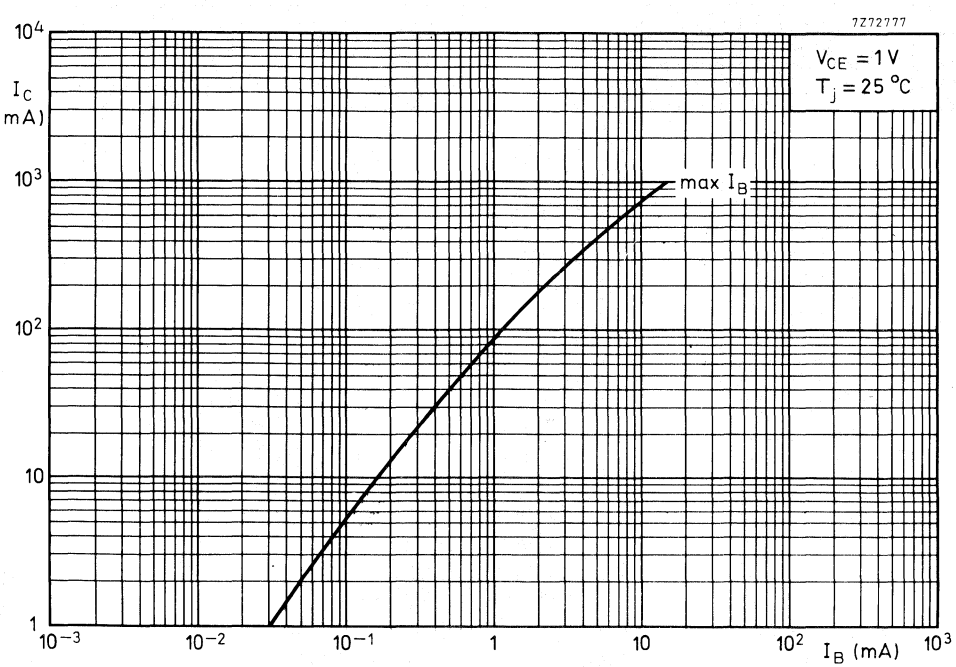


Fig. 5 Typical values collector current as a function of maximum base current.

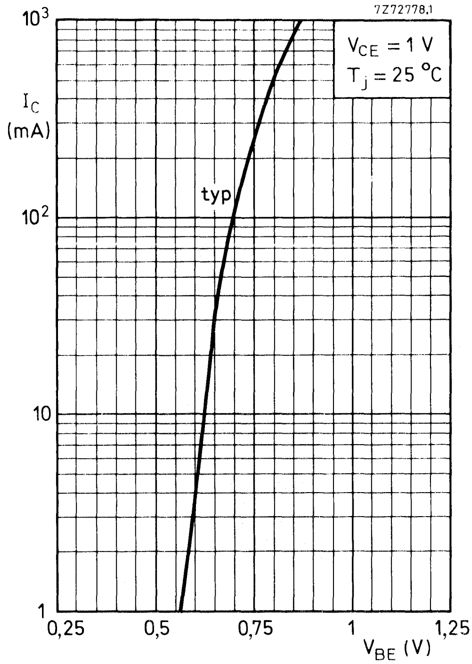


Fig. 6 Typical values collector current as a function of base-emitter voltage.

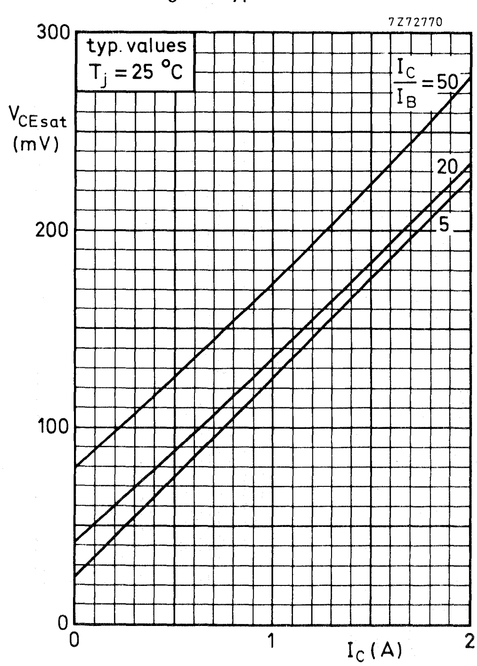


Fig. 7 Collector-emitter saturation voltage as a function of collector current.

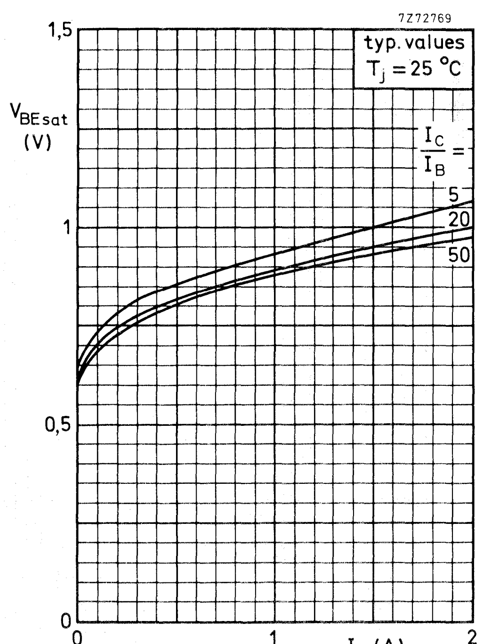


Fig. 8 Base-emitter saturation voltage as a function of collector current.

SILICON PLANAR EPITAXIAL TRANSISTOR

P-N-P transistor in a plastic microminiature envelope, intended for low-voltage, high-current l.f. applications. BC868/BC869 is the matched complementary pair suitable for class-B audio output stages up to 3 W.

QUICK REFERENCE DATA

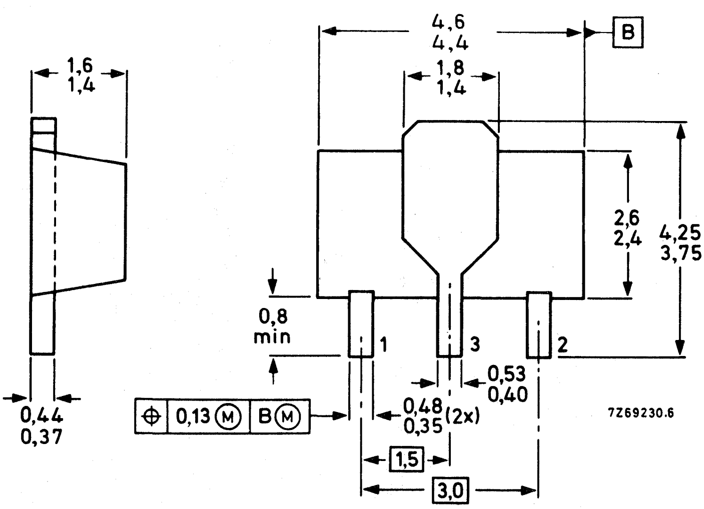
Collector-emitter voltage (V_{BE} = 0)	$-V_{CES}$	max.	25	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	20	V
Collector current (peak value)	$-I_{CM}$	max.	2	A
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	1	W
Junction temperature	T_j	max.	150	°C
D.C. current gain $-I_C$ = 500 mA; $-V_{CE}$ = 1 V	h_{FE}		85 to 375	
Transition frequency at f = 35 MHz $-I_C$ = 10 mA; $-V_{CE}$ = 5 V	f_T	typ.	60	MHz

MECHANICAL DATA

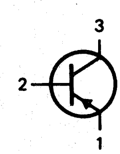
Dimensions in mm

Fig. 1 SOT-89.

Mark
CEC



BOTTOM VIEW



See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-emitter voltage (V_{BE} = 0)	$-V_{CES}$	max.	25	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	20	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5	V
Collector current (d.c.)	$-I_C$	max.	1	A
Collector current (peak value)	$-I_{CM}$	max.	2	A
Base current (d.c.)	$-I_B$	max.	100	mA
Base current (peak value)	$-I_{BM}$	max.	200	mA
Total power dissipation up to T_{amb} = 25 °C*	P_{tot}	max.	1	W
Storage temperature	T_{stg}	−65 to + 150		°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE

From junction to ambient in free air*	$R_{th\ j\text{-}a}$	=	125	K/W
From junction to tab	$R_{th\ j\text{-}t}$	=	10	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current				
I_E = 0; $-V_{CB}$ = 25 V	$-I_{CBO}$	<	10	μA
I_E = 0; $-V_{CB}$ = 25 V; T_j = 150 °C	$-I_{CBO}$	<	1	mA
Emitter cut-off current				
I_C = 0; $-V_{EB}$ = 5 V	$-I_{EBO}$	<	10	μA
Base-emitter voltage				
$-I_C$ = 5 mA; $-V_{CE}$ = 10 V	$-V_{BE}$	typ.	0,62	V
$-I_C$ = 1 A; $-V_{CE}$ = 1 V	$-V_{BE}$	<	1	V
Collector-emitter saturation voltage				
$-I_C$ = 1 A; $-I_B$ = 100 mA	$-V_{CEsat}$	<	0,5	V
D.C. current gain				
$-I_C$ = 5 mA; $-V_{CE}$ = 10 V	h_{FE}	>	50	
$-I_C$ = 500 mA; $-V_{CE}$ = 1 V	h_{FE}		85 to 375	
$-I_C$ = 1 A; $-V_{CE}$ = 1 V	h_{FE}	>	60	
Collector capacitance at f = 450 kHz				
$I_E = I_e$ = 0; $-V_{CB}$ = 5 V	C_c	typ.	45	pF
Transition frequency at f = 35 MHz				
$-I_C$ = 10 mA; $-V_{CE}$ = 5 V	f_T	typ.	60	MHz

* Mounted on a ceramic substrate, area = 2,5 cm^2; thickness = 0,7 mm.

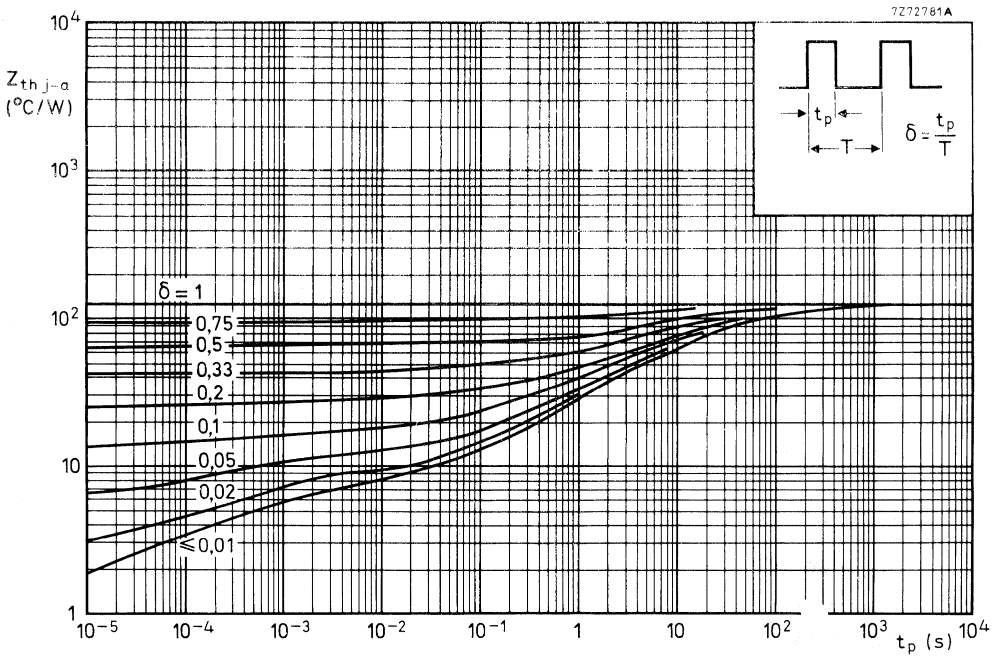


Fig. 2 Pulse power rating chart.

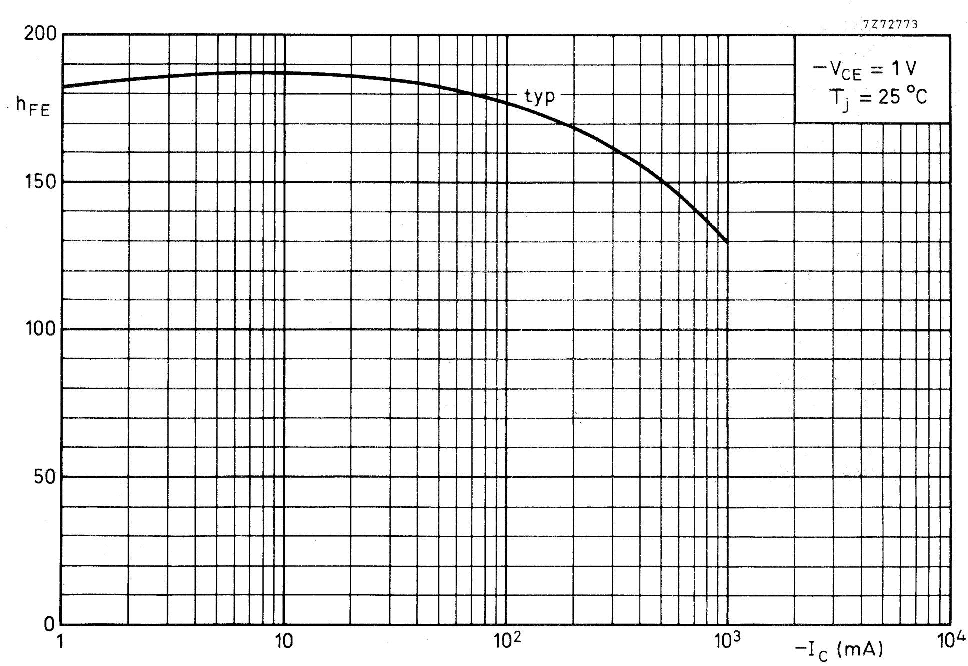


Fig. 3 D.C. current gain.

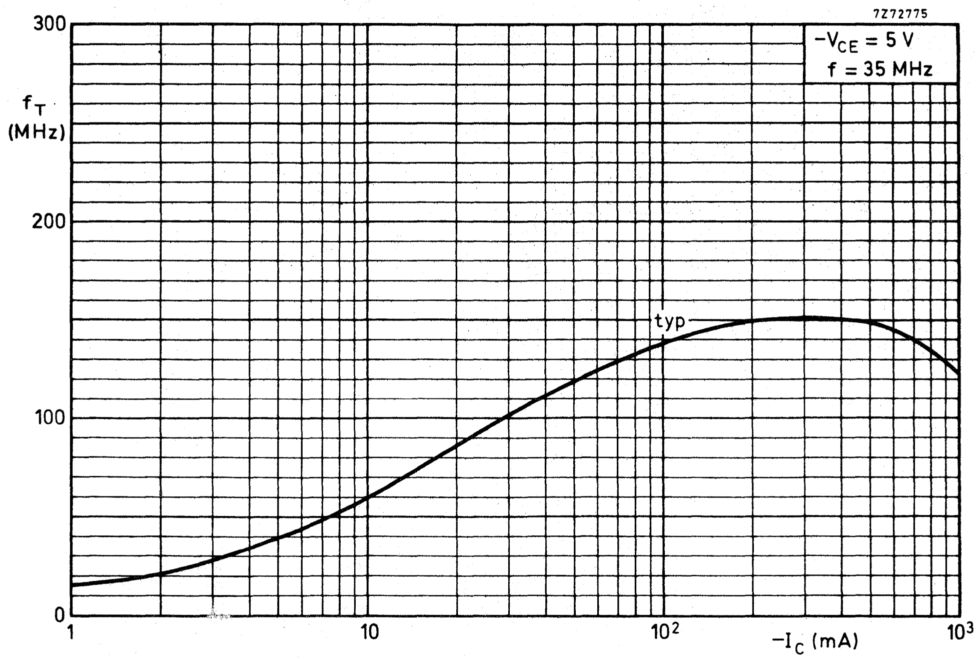


Fig. 4 Typical values transition frequency as a function of collector current.

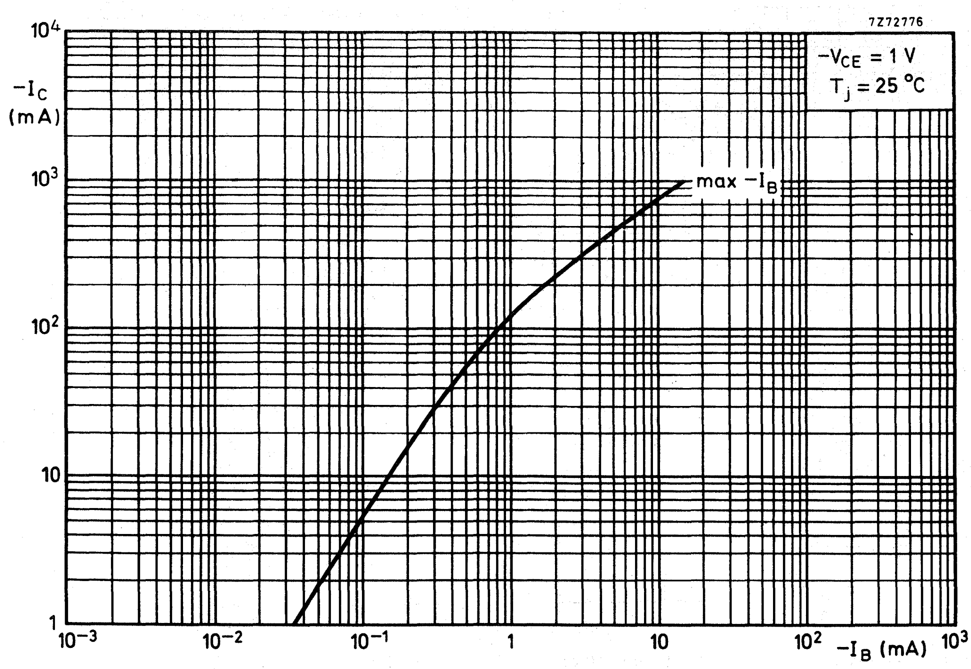


Fig. 5 Typical values collector current as a function of maximum base current.

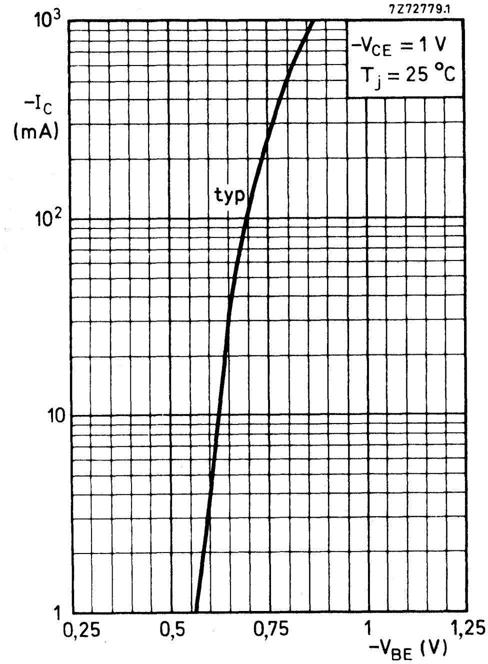


Fig. 6 Typical values collector current as a function of base-emitter voltage.

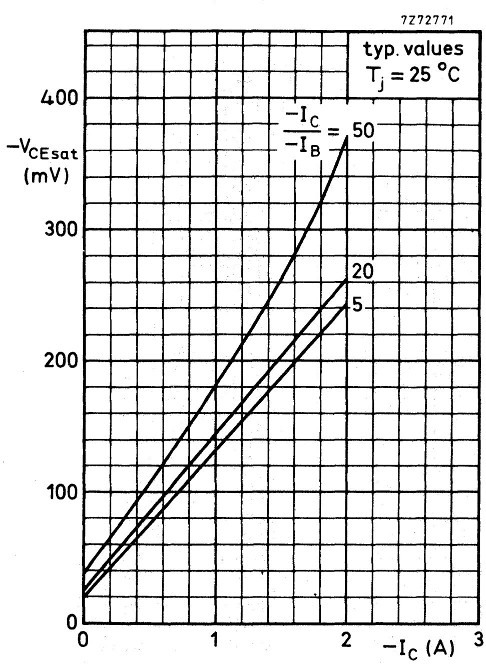


Fig. 7 Collector-emitter saturation voltage as a function of collector current.

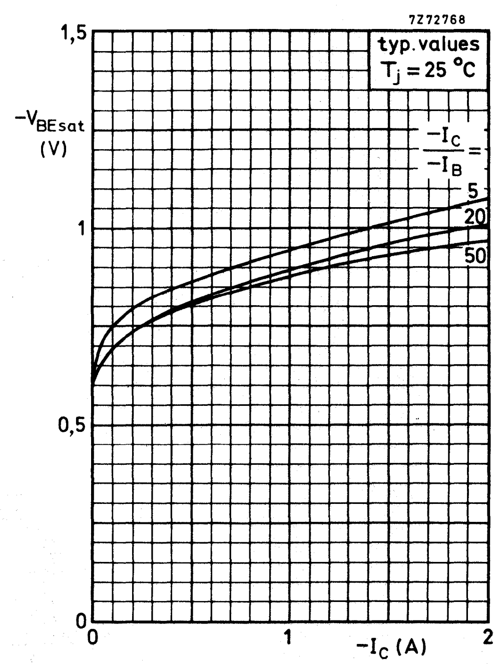


Fig. 8 Base-emitter saturation voltage as a function of collector current.

SILICON PLANAR EPITAXIAL TRANSISTORS

P-N-P transistors, in a microminiature plastic envelope, intended for low level, low noise general purpose applications in thick and thin-film circuits.

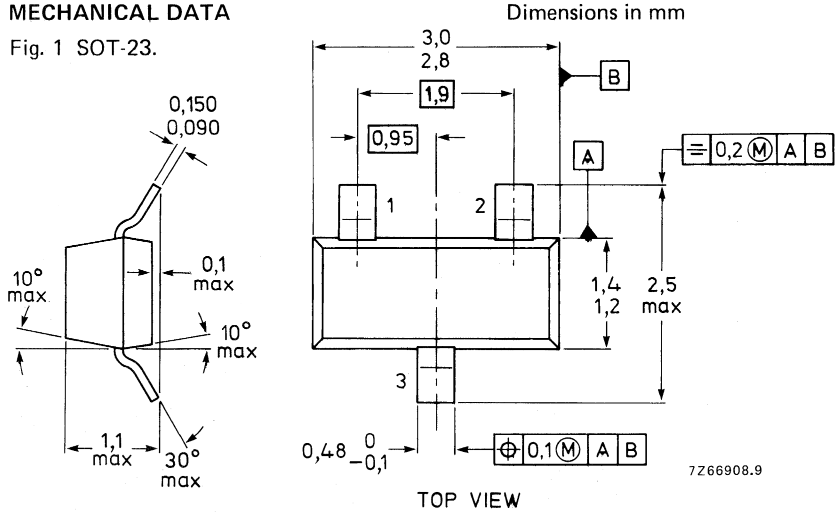
QUICK REFERENCE DATA

			BCF29	BCF30	
D.C. current gain at T_j = 25 °C $-I_C$ = 2 mA; $-V_{CE}$ = 5 V	h_{FE}	> <	120 260	215 500	
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	32		V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	32		V
Collector current (peak value)	$-I_{CM}$	max.	200		mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	350		mW
Junction temperature	T_j	max.	175		°C
Transition frequency at f = 35 MHz $-I_C$ = 10 mA; $-V_{CE}$ = 5 V	f_T	typ.	150		MHz
Noise figure at R_S = 2 kΩ $-I_C$ = 200 μA; $-V_{CE}$ = 5 V; f = 1 kHz; B = 200 Hz	F	<	4		dB

MECHANICAL DATA

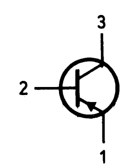
Dimensions in mm

Fig. 1 SOT-23.

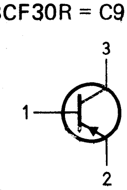


Marking code

BCF29 = C7
BCF30 = C8



BCF29R = C77
BCF30R = C9



R-types are available on request.

See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	32 V
Collector-emitter voltage (V_{BE} = 0)	$-V_{CES}$	max.	32 V
Collector-emitter voltage (open base) $-I_C$ = 2 mA	$-V_{CEO}$	max.	32 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5 V
Collector current (d.c.)	$-I_C$	max.	100 mA
Collector current (peak value)	$-I_{CM}$	max.	200 mA
Total power dissipation up to T_{amb} = 25 °C**	P_{tot}	max.	350 mW
Storage temperature	T_{stg}		−65 to + 175 °C
Junction temperature	T_j	max.	175 °C

THERMAL CHARACTERISTICS *

$T_j = P \times (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	50 K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280 K/W
From soldering points to ambient**	$R_{th\ s\text{-}a}$	=	90 K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current			
I_E = 0; $-V_{CB}$ = 32 V	$-I_{CBO}$	<	100 nA
I_E = 0; $-V_{CB}$ = 32 V; T_j = 100 °C	$-I_{CBO}$	<	10 μA
Base-emitter voltage			
$-I_C$ = 2 mA; $-V_{CE}$ = 5 V	$-V_{BE}$		600 to 750 mV
Saturation voltages			
$-I_C$ = 10 mA; $-I_B$ = 0,5 mA	$-V_{CEsat}$	typ.	80 mV
		<	300 mV
	$-V_{BEsat}$	typ.	720 mV
$-I_C$ = 50 mV; $-I_B$ = 2,5 mA	$-V_{CEsat}$	typ.	150 mV
	$-V_{BEsat}$	typ.	810 mV

* See *Thermal characteristics.*
** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

D.C. current gain

			BCF29	BCF30	
$-I_C = 10\ \mu A; -V_{CE} = 5\ V$	h_{FE}	typ.	90	150	
$-I_C = 2\ mA; -V_{CE} = 5\ V$	h_{FE}	>	120	215	
		<	260	500	
Collector capacitance at f = 1 MHz; $I_E = I_e = 0; -V_{CB} = 10\ V$	C_c	typ.	4,5		pF ←
Transition frequency at f = 35 MHz; $-I_C = 10\ mA; -V_{CE} = 5\ V$	f_T	typ.	150		MHz
Noise figure at $R_S = 2\ k\Omega$; $-I_C = 200\ \mu A; -V_{CE} = 5\ V$; f = 1 kHz; B = 200 Hz	F	<	4		dB
		typ.	1		dB

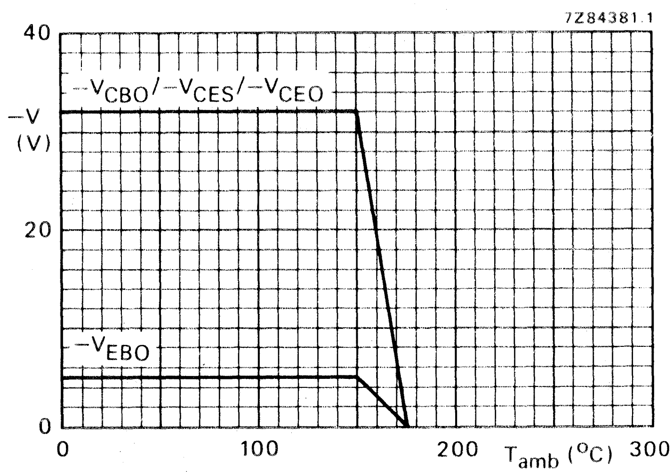


Fig. 2 Voltage derating curves.

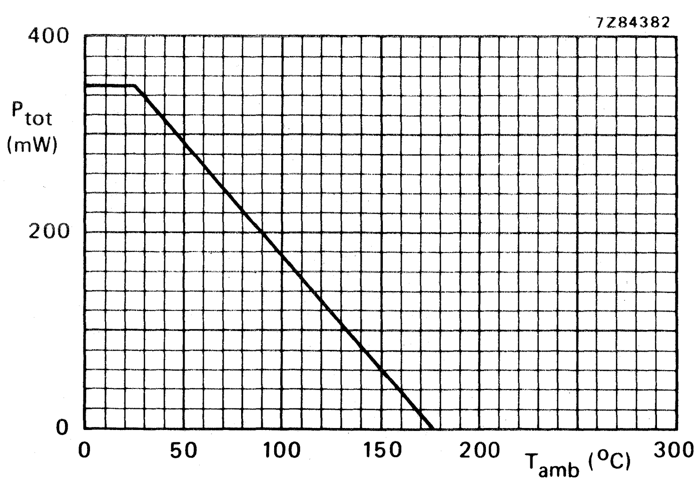


Fig. 3 Power derating curve.

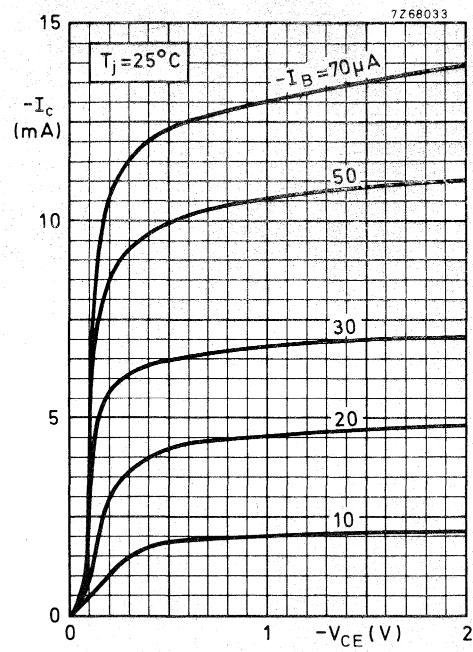


Fig. 4.

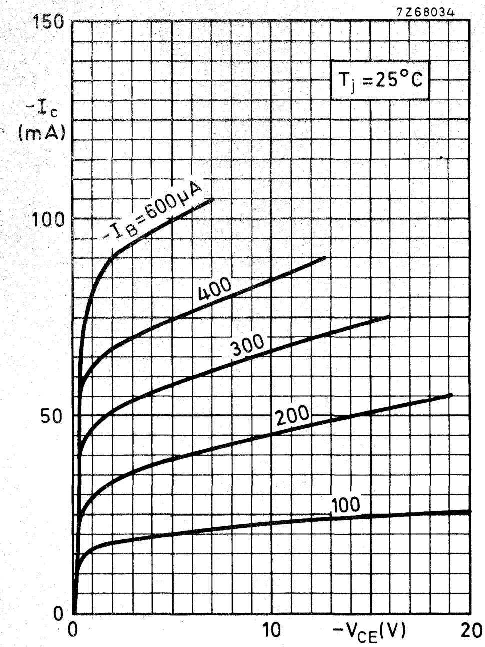


Fig. 5.

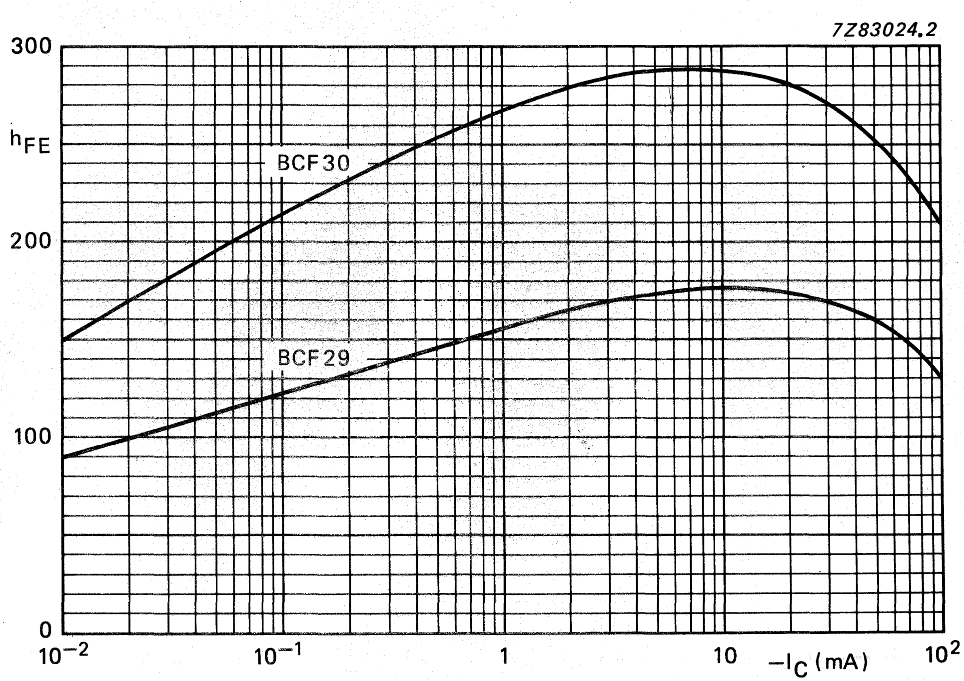


Fig. 6 Typical values of d.c. current gain. $-V_{CE} = 5$ V; $T_j = 25$ °C.

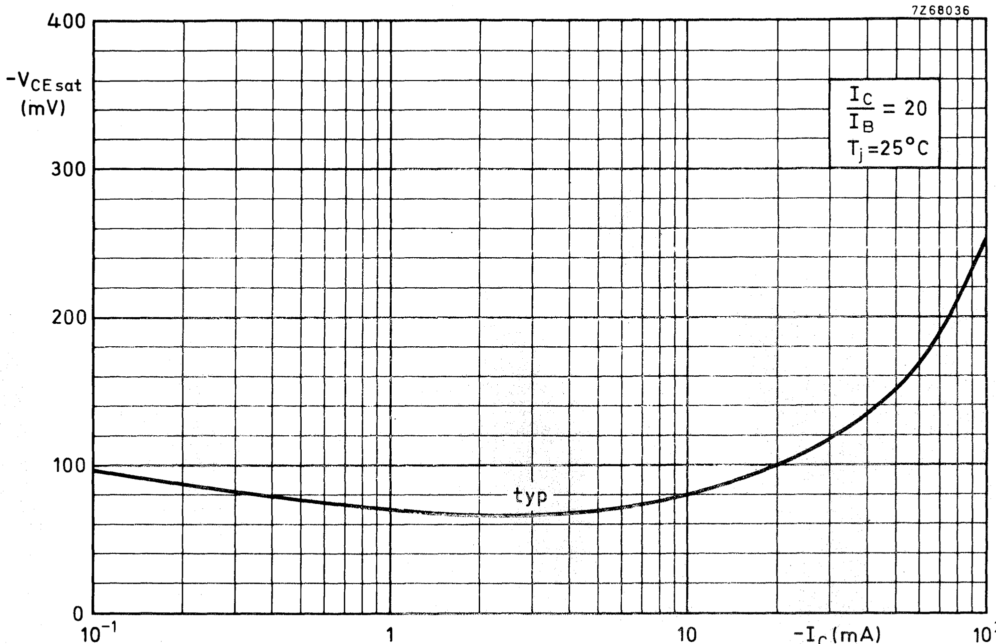

7Z68036
400
$-V_{CEsat}$ (mV)
300
200
100
0
I_C/I_B = 20
T_j = 25 °C
typ
10^{-1}
1
10
$-I_C$ (mA)
10^2

Fig. 7.

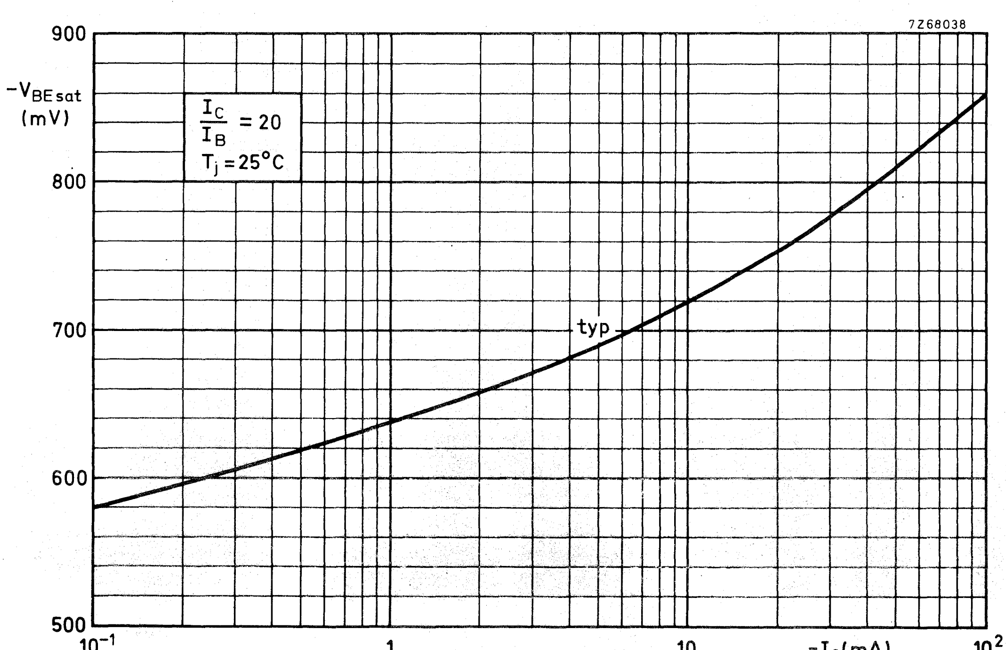

7Z68038
900
$-V_{BEsat}$ (mV)
800
700
600
500
I_C/I_B = 20
T_j = 25 °C
typ
10^{-1}
1
10
$-I_C$ (mA)
10^2

Fig. 8.

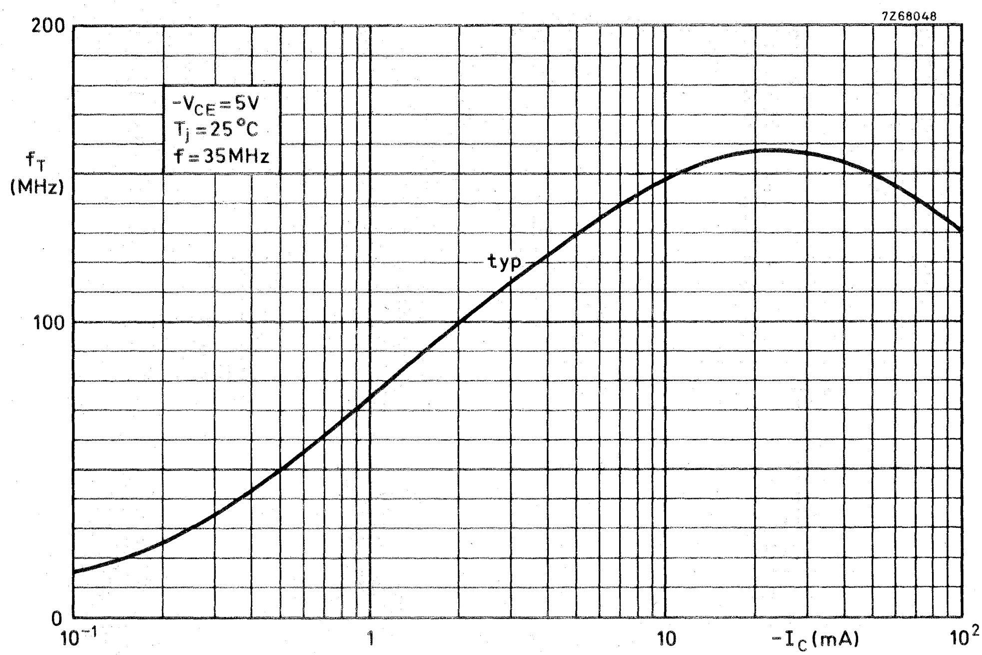


Fig. 9.

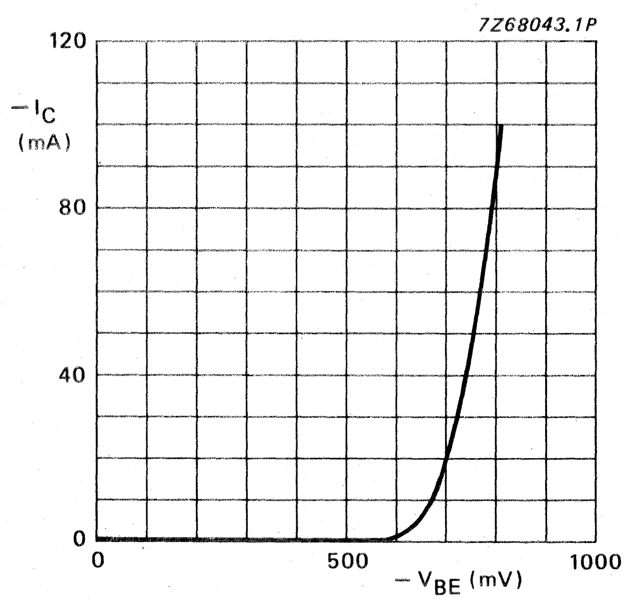


Fig. 10 $-V_{CE}$ = 5 V; T_j = 25 °C; typical values.

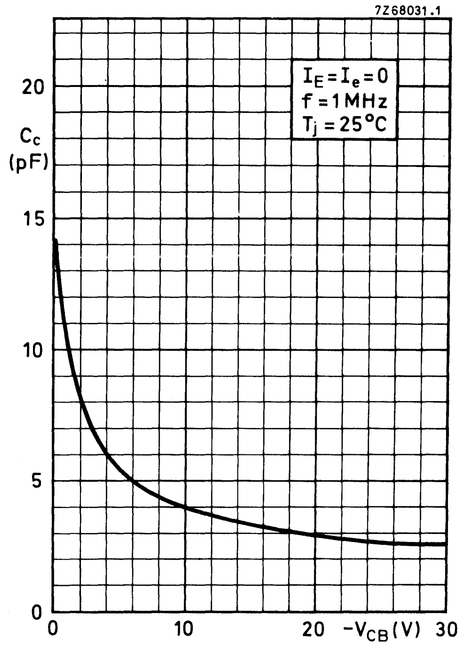

7Z68031.1
$I_E = I_e = 0$
f = 1 MHz
$T_j = 25\,^\circ C$
C_c
(pF)
20
15
10
5
0
0
10
20
$-V_{CB}$ (V)
30

Fig. 11.

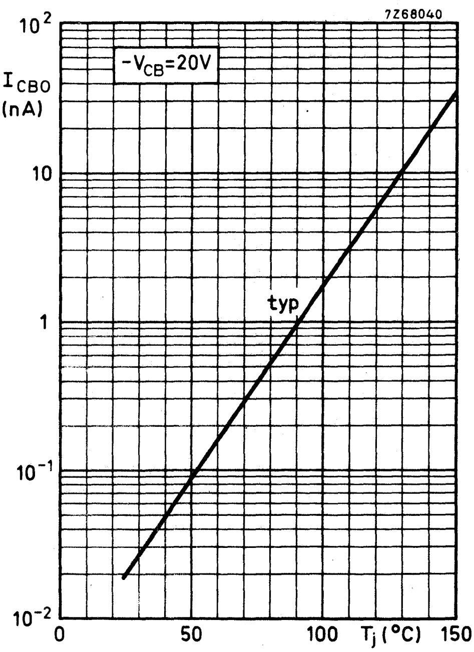

7Z68040
$-V_{CB} = 20V$
$-I_{CBO}$
(nA)
10^2
10
1
10^{-1}
10^{-2}
typ
0
50
100
T_j (°C)
150

Fig. 12.

SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N transistors in a microminiature plastic envelope. They are intended for low level, low noise general purpose applications in thick and thin-film circuits.

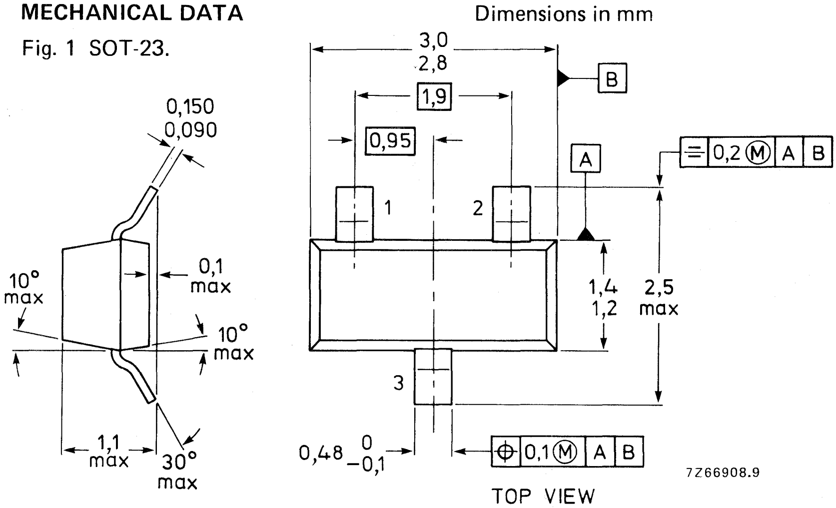
QUICK REFERENCE DATA

			BCF32	BCF33	
D.C. current gain at T_j = 25 °C; I_C = 2 mA; V_{CE} = 5 V	h_{FE}	>	200	420	
		<	450	800	
Collector-base voltage (open emitter)	V_{CBO}	max.	32		V
Collector-emitter voltage (open base)	V_{CEO}	max.	32		V
Collector current (peak value)	I_{CM}	max.	200		mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	350		mW
Junction temperature	T_j	max.	175		°C
Transition frequency at f = 35 MHz; I_C = 2 mA; V_{CE} = 5 V	f_T	typ.	300		MHz
Noise figure at R_S = 2 kΩ; I_C = 200 μA; V_{CE} = 5 V; f = 1 kHz; B = 200 Hz	F	<	4		dB

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-23.

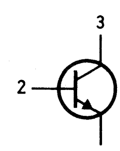


R-types are available on request.

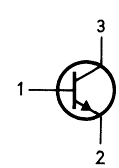
See also *Soldering recommendations.*

Marking code

BCF32 = D7
BCF33 = D8



BCF32R = D77
BCF33R = D81



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	V_{CBO}	max.	32	V
Collector-emitter voltage (open base) I_C = 2 mA	V_{CEO}	max.	32	V
Emitter-base voltage (open collector)	V_{EBO}	max.	5	V
Collector current (d.c.)	I_C	max.	100	mA
Collector current (peak value)	I_{CM}	max.	200	mA
Total power dissipatation up to T_{amb} = 25 °C**	P_{tot}	max.	350	mW
Storage temperature	T_{stg}	−65 to + 175		°C
Junction temperature	T_j	max.	175	°C

THERMAL CHARACTERISTICS*

$T_j = P \times (R_{th\,j\text{-}t} + R_{th\,t\text{-}s} + R_{th\,s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\,j\text{-}t}$	=	50	K/W
From tab to soldering points	$R_{th\,t\text{-}s}$	=	280	K/W
From soldering points to ambient**	$R_{th\,s\text{-}a}$	=	90	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current				
$I_E = 0$; V_{CB} = 32 V	I_{CBO}	<	100	nA
$I_E = 0$; V_{CB} = 32 V; T_j = 100 °C	I_{CBO}	<	10	μA
Base-emitter voltage				
I_C = 2 mA; V_{CE} = 5 V	V_{BE}	550 to 700		mV
Saturation voltages				
I_C = 10 mA; I_B = 0,5 mA	V_{CEsat}	typ.	120	mV
		<	250	mV
	V_{BEsat}	typ.	750	mV
I_C = 50 mA; I_B = 2,5 mA	V_{CEsat}	typ.	210	mV
	V_{BEsat}	typ.	850	mV

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

			BCF32	BCF33
D.C. current gain				
$I_C = 10\ \mu A$; $V_{CE} = 5\ V$	h_{FE}	typ.	150	270
		>	200	420
$I_C = 2\ mA$; $V_{CE} = 5\ V$	h_{FE}	<	450	800
Collector capacitance at f = 1 MHz				
$I_E = I_e = 0$; $V_{CB} = 10\ V$	C_c	typ.	2,5 pF	
Transition frequency at f = 35 MHz				
$I_C = 10\ mA$; $V_{CE} = 5\ V$	f_T	typ.	300 MHz	
Noise figure at $R_S = 2\ k\Omega$				
$I_C = 200\ \mu A$; $V_{CE} = 5\ V$; f = 1 kHz; B = 200 Hz	F	<	4 dB	
		typ.	1,2 dB	

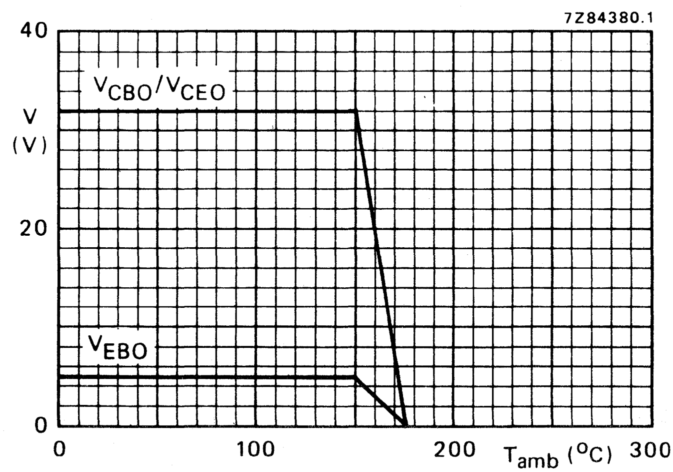


Fig. 2 Voltage derating curves.

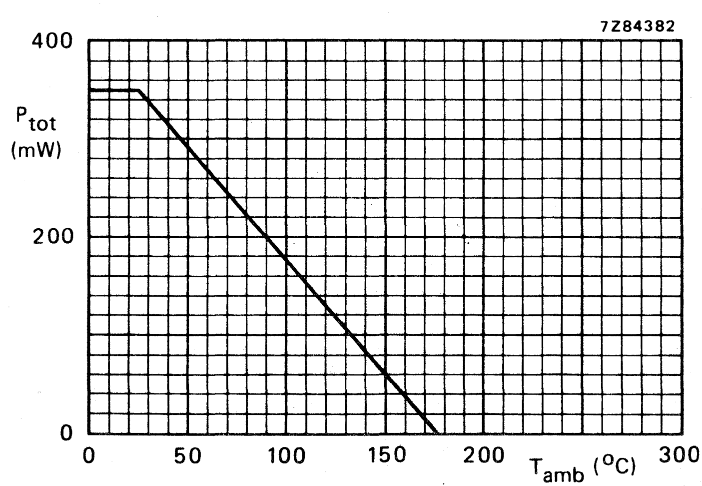


Fig. 3 Power derating curve.

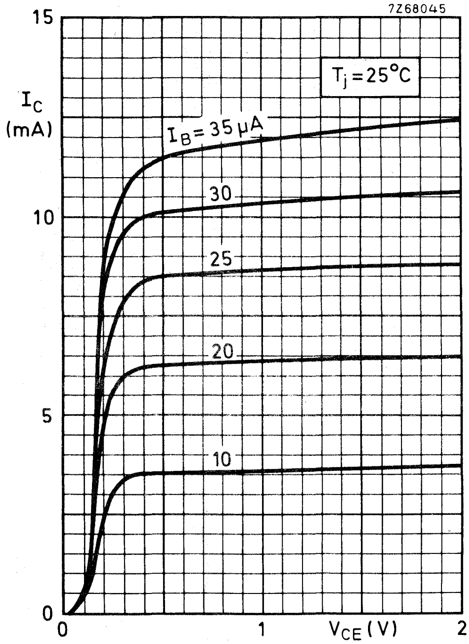


Fig. 4.

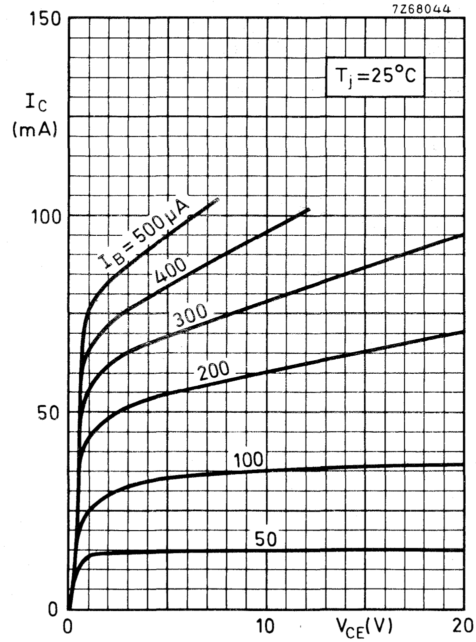


Fig. 5.

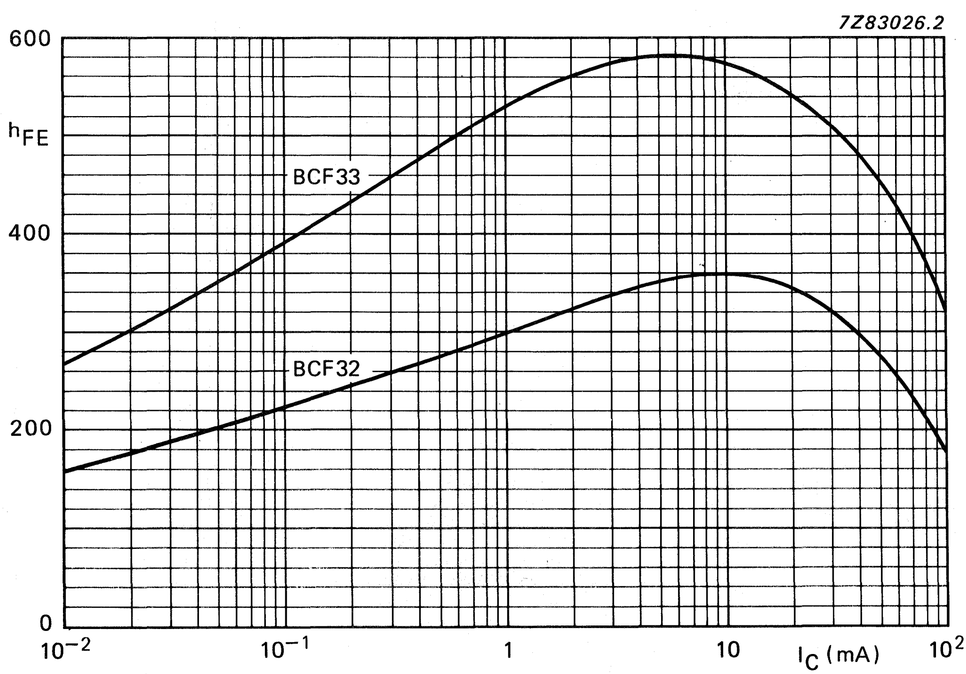


Fig. 6 Typical values d.c. current gain. V_{CE} = 5 V; T_j = 25 ^oC.

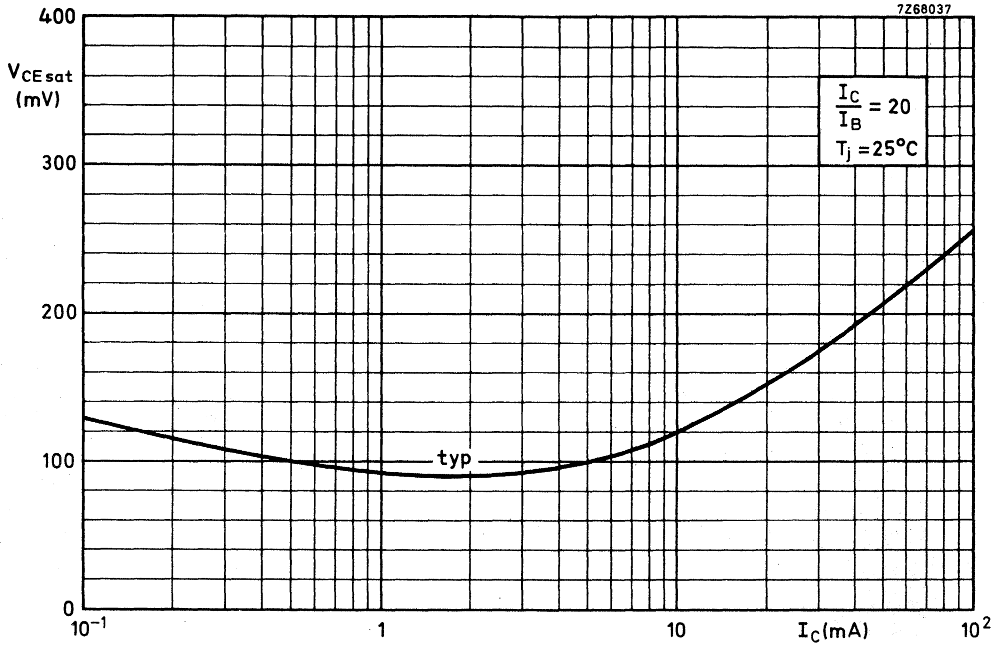

7Z68037
400
V_{CEsat}
(mV)
300
200
100
0
$\frac{I_C}{I_B} = 20$
$T_j = 25°C$
typ
10^{-1}
1
10
I_C(mA)
10^2

Fig. 7.

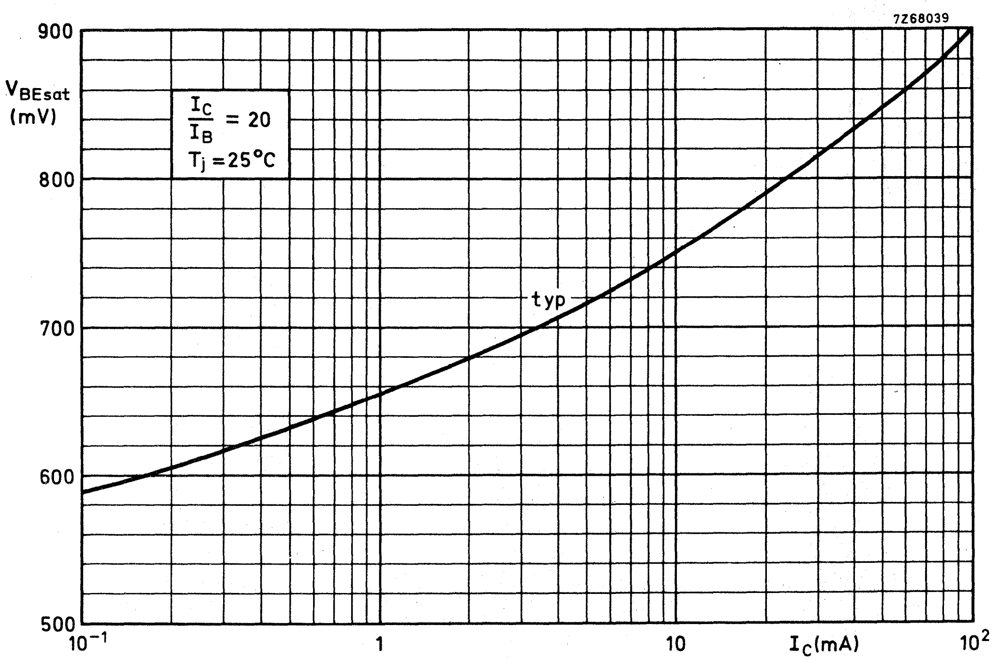

7Z68039
900
V_{BEsat}
(mV)
800
700
600
500
$\frac{I_C}{I_B} = 20$
$T_j = 25°C$
typ
10^{-1}
1
10
I_C(mA)
10^2

Fig. 8.

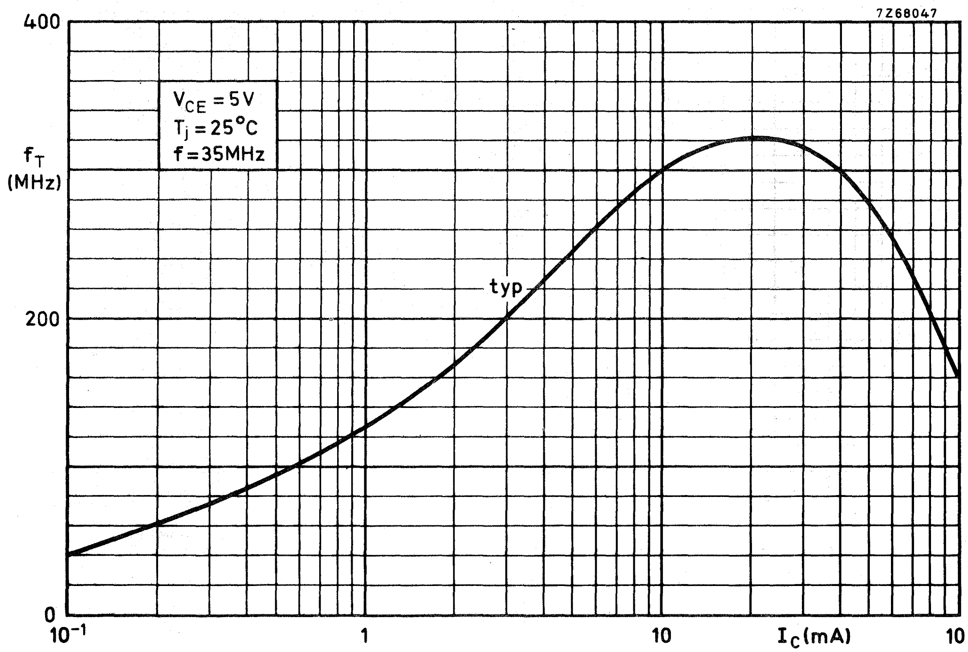


Fig. 9.

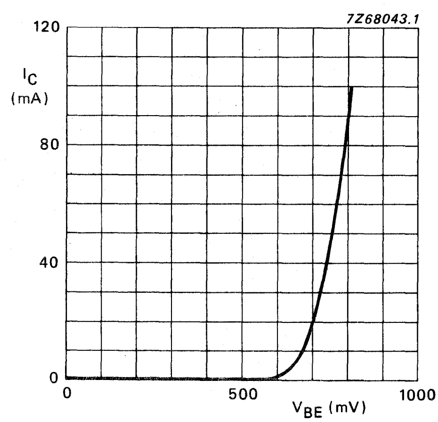


Fig. 10 $V_{CE} = 5$ V; $T_j = 25$ °C; typical values.

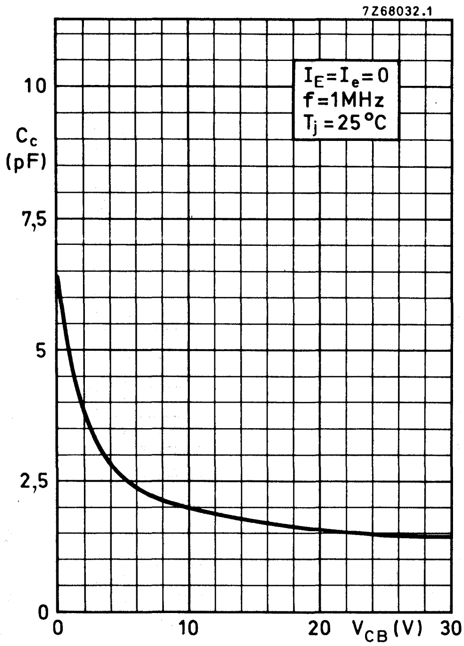

7Z68032.1
$I_E = I_e = 0$
f = 1MHz
T_j = 25 °C
C_c (pF)
10
7,5
5
2,5
0
0
10
20
V_{CB} (V)
30

Fig. 11.

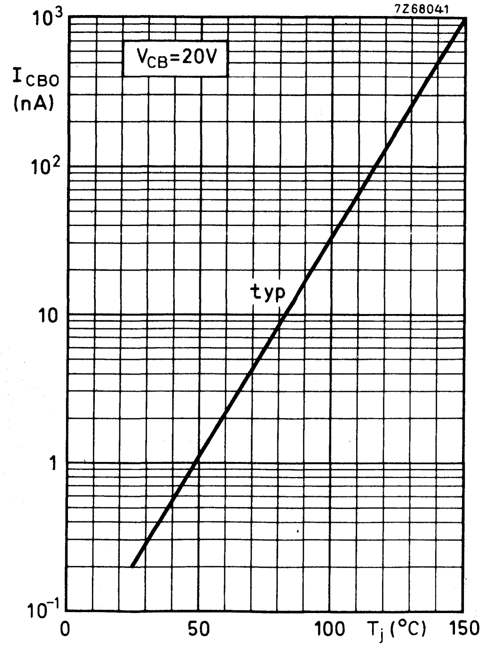

7Z68041
V_{CB}=20V
I_{CBO} (nA)
10^3
10^2
10
1
10^{-1}
typ
0
50
100
T_j (°C)
150

Fig. 12.

SILICON PLANAR EPITAXIAL TRANSISTORS

P-N-P transistors, in a microminiature plastic envelope, intended for low level, low noise applications in thick and thin-film circuits.

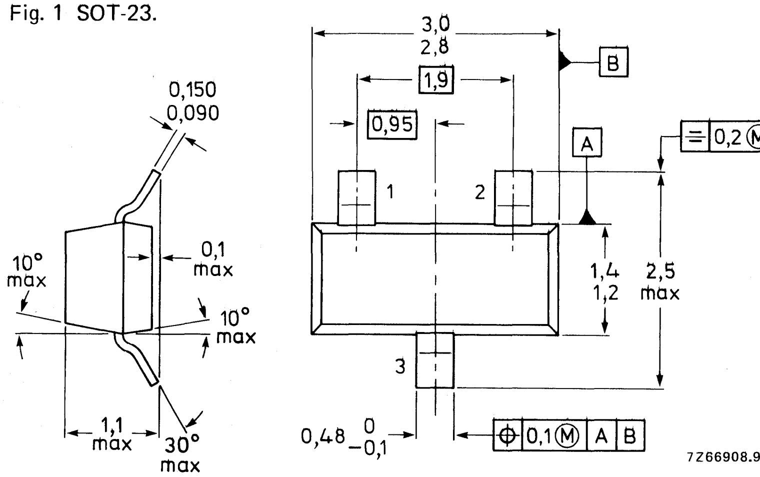
QUICK REFERENCE DATA

D.C. current gain at T_j = 25 °C $-I_C$ = 2 mA; $-V_{CE}$ = 5 V	h_{FE}	> <	215 500
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	50 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	45 V
Collector current (peak value)	$-I_{CM}$	max.	200 mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	350 mW
Junction temperature	T_j	max.	175 °C
Transition frequency at f = 35 MHz $-I_C$ = 10 mA; $-V_{CE}$ = 5 V	f_T	typ.	150 MHz
Noise figure at R_S = 2 kΩ $-I_C$ = 200 μA; $-V_{CE}$ = 5 V; f = 1 kHz; B = 200 Hz	F	<	4 dB

MECHANICAL DATA

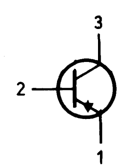
Dimensions in mm

Fig. 1 SOT-23.

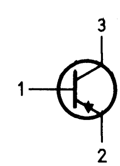


Marking code

BCF70 = H7



BCF70R = H71



R-types are available on request.

See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter) see Fig. 2	$-V_{CBO}$	max.	50	V
Collector-emitter voltage (V_{BE} = 0) see Fig. 2	$-V_{CES}$	max.	50	V
Collector-emitter voltage (open base) see Fig. 2 $-I_C$ = 2 mA	$-V_{CEO}$	max.	45	V
Emitter-base voltage (open collector) see Fig. 2	$-V_{EBO}$	max.	5	V
Collector current (d.c.)	$-I_C$	max.	100	mA
Collector current (peak value)	$-I_{CM}$	max.	200	mA
Total power dissipation up to T_{amb} = 25 °C**	P_{tot}	max.	350	mW
Storage temperature	T_{stg}	−65 to + 175		°C
Junction temperature	T_j	max.	175	°C

THERMAL CHARACTERISTICS*

$T_j = Px\,(R_{th\,j\text{-}t} + R_{th\,t\text{-}s} + R_{th\,s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\,j\text{-}t}$	=	50	K/W
From tab to soldering points	$R_{th\,t\text{-}s}$	=	280	K/W
From soldering points to ambient**	$R_{th\,s\text{-}a}$	=	90	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

I_E = 0; $-V_{CB}$ = 20 V; T_j = 25 °C	$-I_{CBO}$	<	100	nA
T_j = 100 °C	$-I_{CBO}$	<	10	μA
Base-emitter voltage $-I_C$ = 2 mA; $-V_{CE}$ = 5 V; T_j = 25 °C	$-V_{BE}$	600 to 750		mV
Saturation voltages $-I_C$ = 10 mA; $-I_B$ = 0,5 mA	$-V_{CEsat}$	typ.	80	mV
		<	300	mV
	$-V_{BEsat}$	typ.	720	mV
$-I_C$ = 50 mA; $-I_B$ = 2,5 mA	$-V_{CEsat}$	typ.	150	mV
	$-V_{BEsat}$	typ.	810	mV

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

D.C. current gain			
$-I_C = 10\ \mu A$; $-V_{CE} = 5$ V	h_{FE}	typ.	150
$-I_C = 2$ mA; $-V_{CE} = 5$ V	h_{FE}	> <	215 500
Collector capacitance at f = 1 MHz			
$I_E = I_e = 0$; $-V_{CB} = 10$ V	C_c	typ.	4,5 pF ←
Transition frequency at f = 35 MHz			
$-I_C = 10$ mA; $-V_{CE} = 5$ V	f_T	typ.	150 MHz
Noise figure at $R_S = 2\ k\Omega$			
$-I_C = 200\ \mu A$; $-V_{CE} = 5$ V f = 1 kHz; B = 200 Hz	F	< typ.	4 dB 1 dB

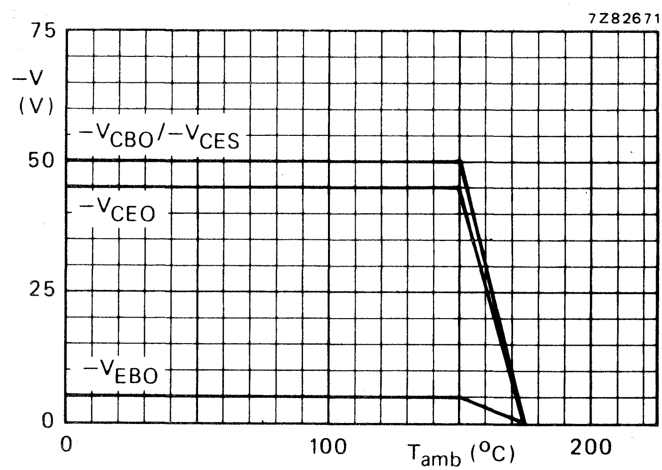


Fig. 2 Voltage derating curves.

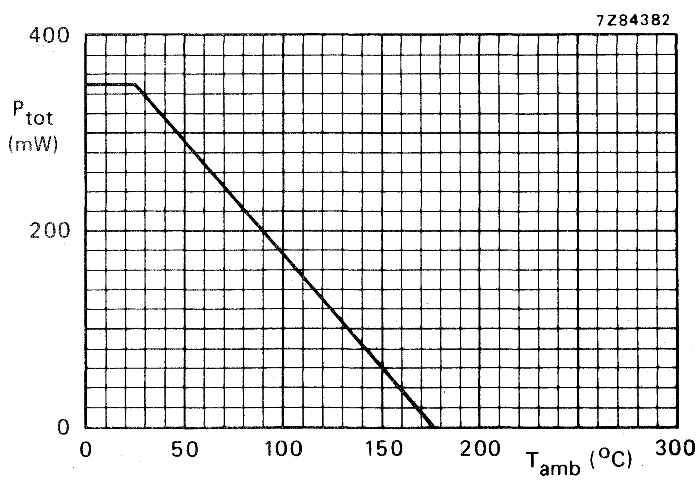


Fig. 3 Power derating curve.

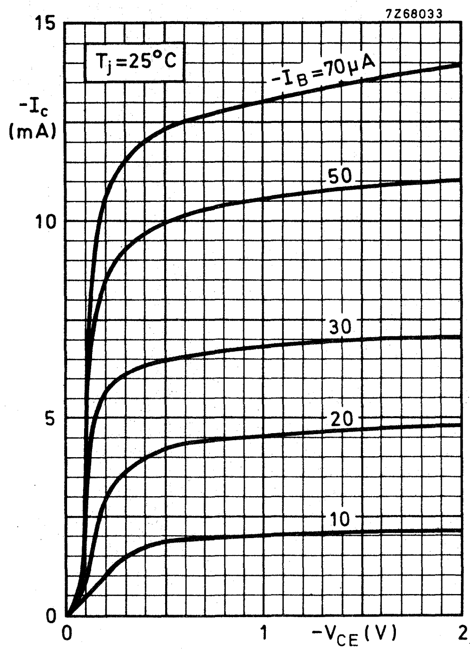


Fig. 4.

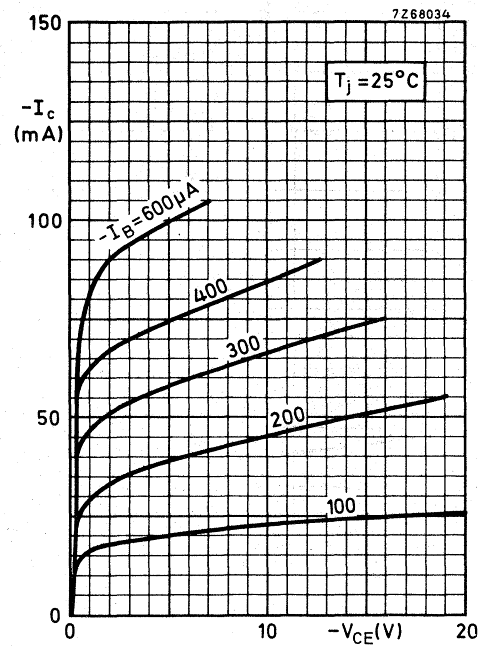


Fig. 5.

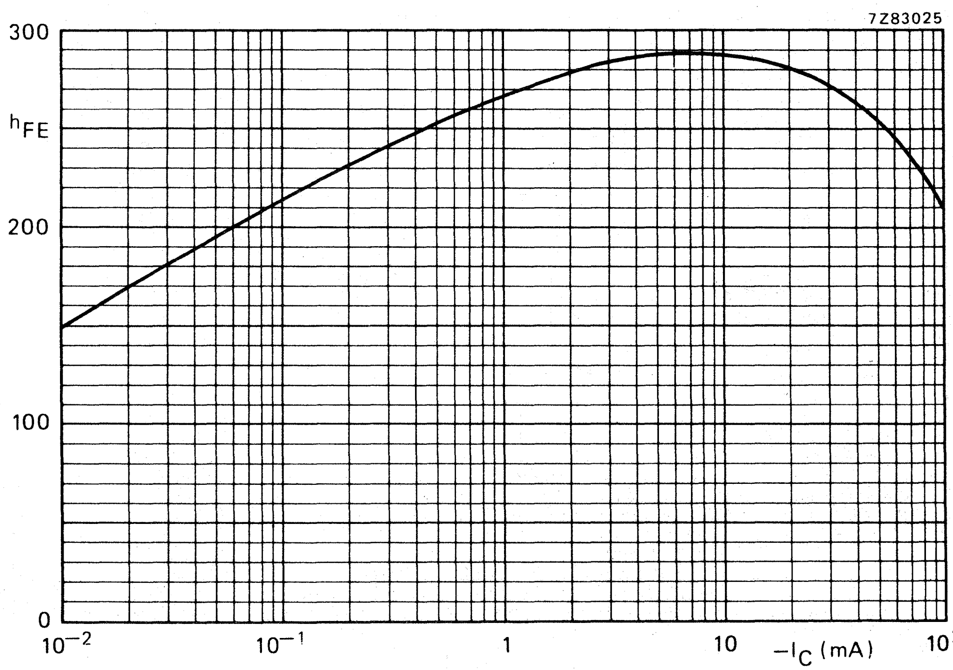


Fig. 6 Typical values of d.c. current gain. $-V_{CE} = 5$ V; $T_j = 25\ ^{o}C$.

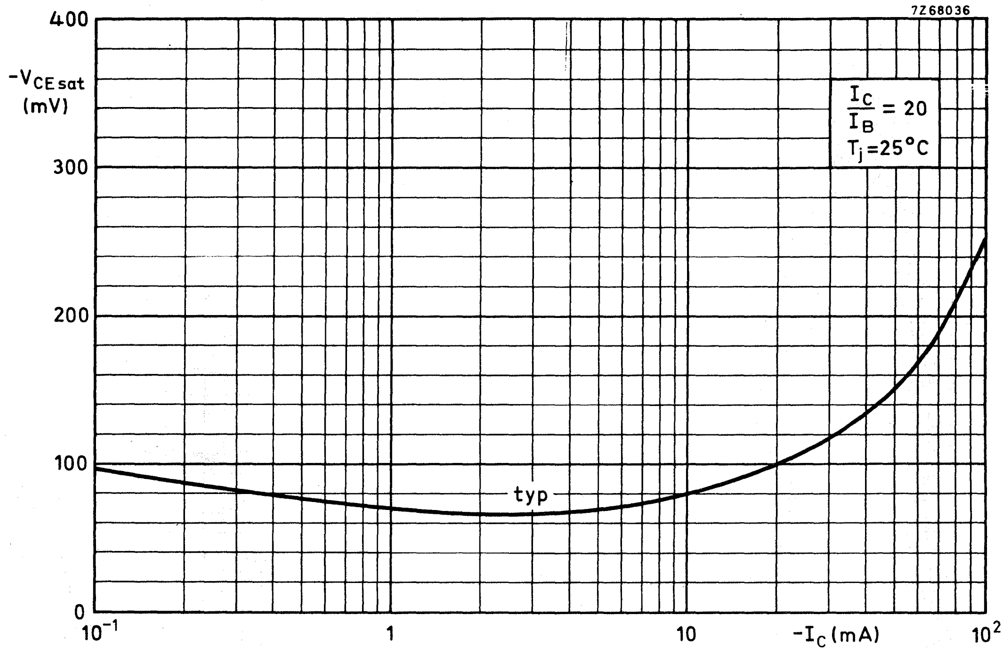

7Z68036
400
300
200
100
0
$-V_{CEsat}$ (mV)
$\frac{I_C}{I_B} = 20$
$T_j = 25\,°C$
typ
10^{-1}
1
10
$-I_C$ (mA)
10^2

Fig. 7.

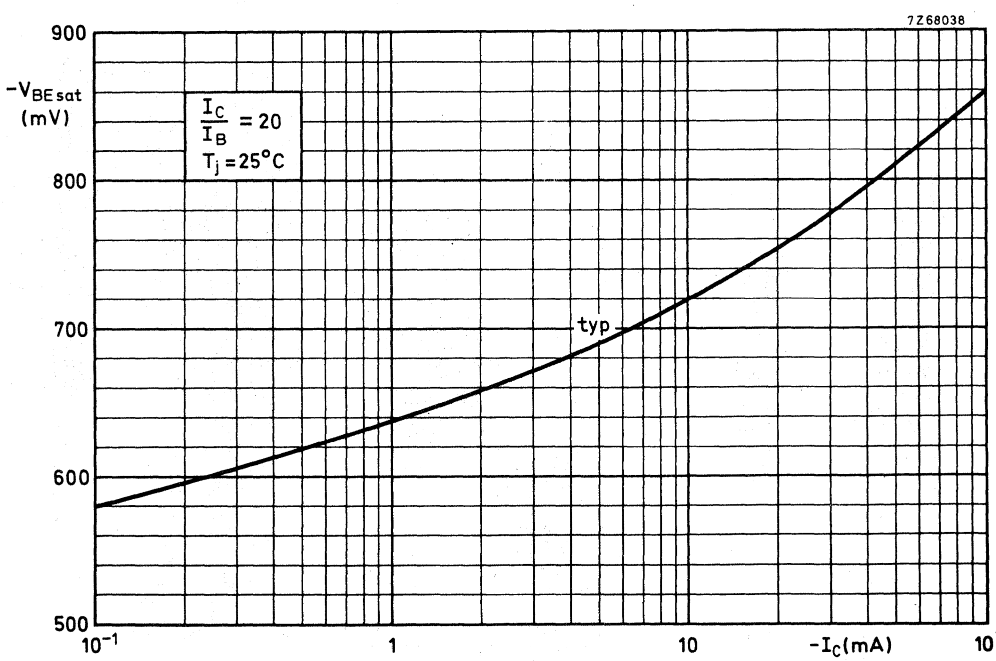

7Z68038
900
800
700
600
500
$-V_{BEsat}$ (mV)
$\frac{I_C}{I_B} = 20$
$T_j = 25\,°C$
typ
10^{-1}
1
10
$-I_C$ (mA)
10^2

Fig. 8.

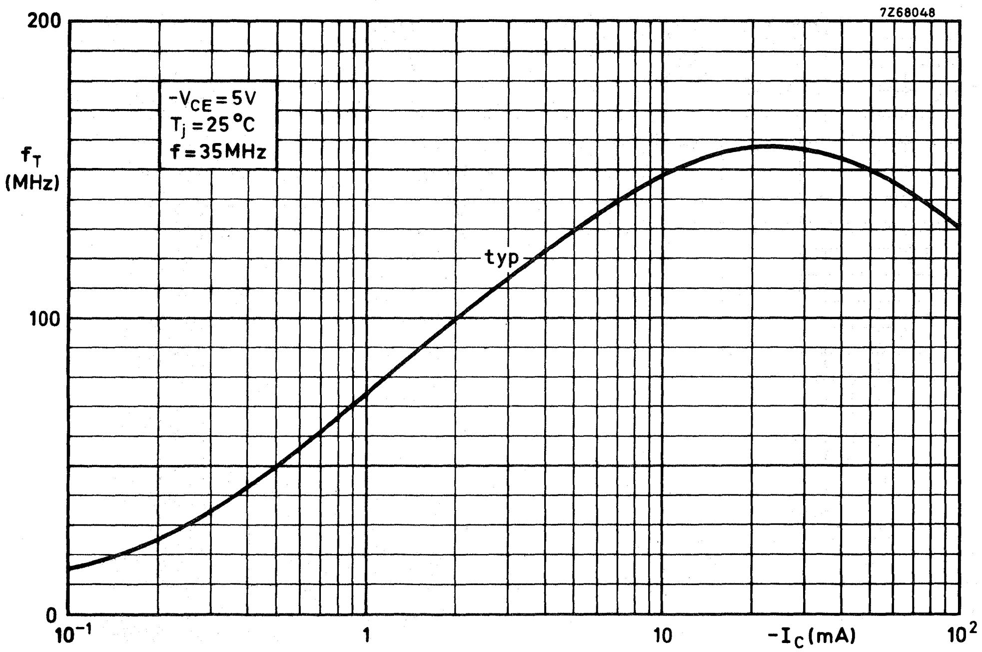


Fig. 9.

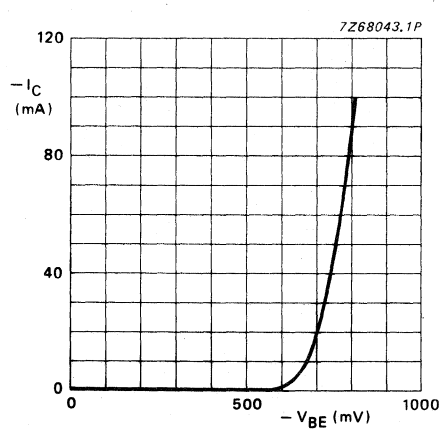


Fig. 10 $-V_{CE}$ = 5 V; T_j = 25 ^oC; typical values.

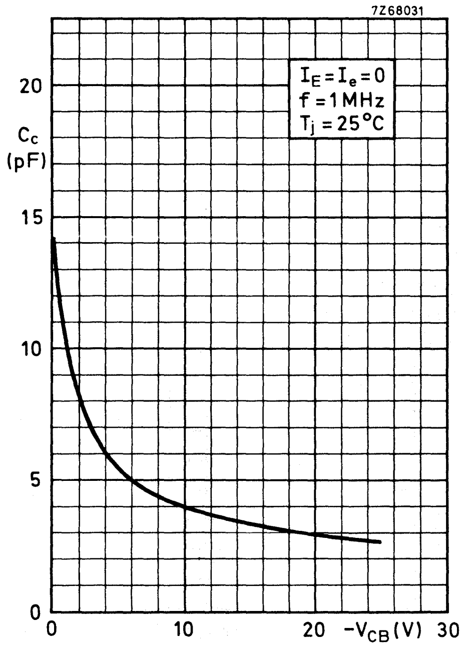

7Z68031
$I_E = I_e = 0$
f = 1 MHz
T_j = 25 °C
20
C_c
(pF)
15
10
5
0
0
10
20
$-V_{CB}$ (V)
30

Fig. 11.

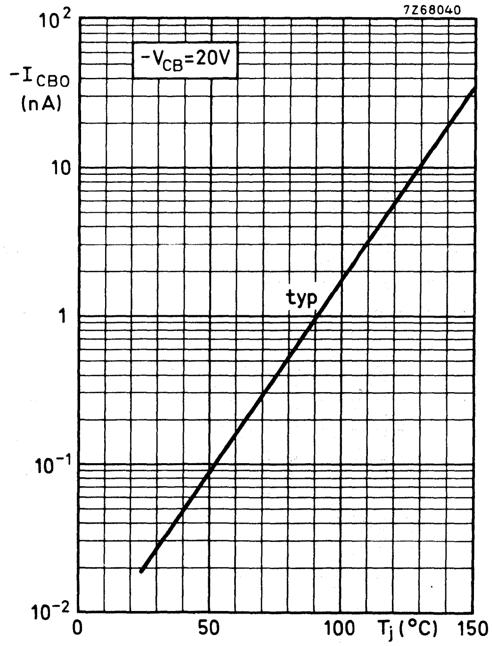

7Z68040
10^2
$-I_{CBO}$
(nA)
$-V_{CB}$=20V
10
typ
1
10^{-1}
10^{-2}
0
50
100
T_j (°C)
150

Fig. 12.

SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N transistors, in a microminiature plastic envelope, intended for low level, low noise general purpose applications in thick and thin-film circuits.

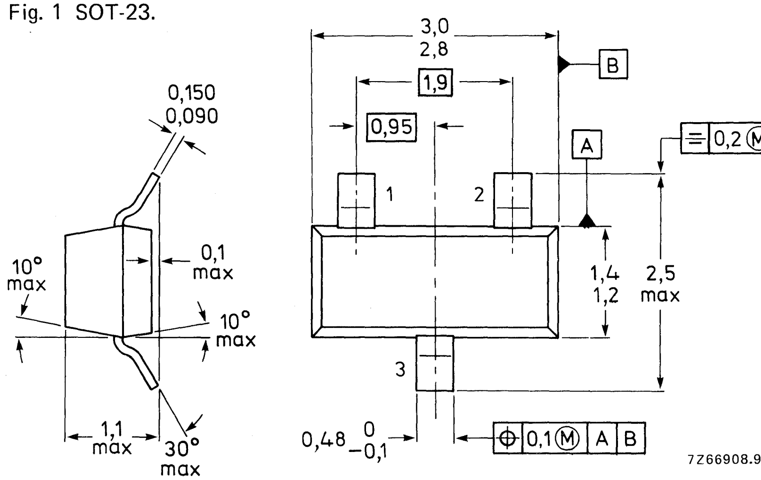
QUICK REFERENCE DATA

Collector-base voltage (open emitter)	V_{CBO}	max.	50 V
Collector-emitter voltage (open base)	V_{CEO}	max.	45 V
Collector current (peak value)	I_{CM}	max.	200 mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	350 mW
Junction temperature	T_j	max.	175 °C
D.C. current gain at T_j = 25 °C I_C = 2 mA; V_{CE} = 5 V	h_{FE}	> <	420 800
Transition frequency at f = 35 MHz I_C = 10 mA; V_{CE} = 5 V	f_T	typ.	300 MHz
Noise figure at R_S = 2 kΩ I_C = 200 μA; V_{CE} = 5 V; f = 1 kHz; B = 200 Hz	F	<	4 dB

MECHANICAL DATA

Dimensions in mm

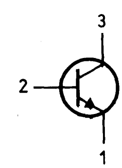
Fig. 1 SOT-23.



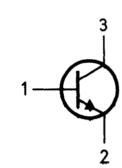
TOP VIEW

Marking code

BCF81 = K9



BCF81R = K91



R-types are available on request

See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter) see Fig. 2	V_{CBO}	max.	50	V
Collector-emitter voltage (open base) see Fig. 2 I_C = 2 mA	V_{CEO}	max.	45	V
Emitter-base voltage (open collector) see Fig. 2	V_{EBO}	max.	5	V
Collector current (d.c.)	I_C	max.	100	mA
Collector current (peak value)	I_{CM}	max.	200	mA
Total power dissipation up to T_{amb} = 25 °C**	P_{tot}	max.	350	mW
Storage temperature	T_{stg}	−65 to + 175		°C
Junction temperature	T_j	max.	175	°C

THERMAL CHARACTERISTICS*

$T_j = Px\,(R_{th\,j\text{-}t} + R_{th\,t\text{-}s} + R_{th\,s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\,j\text{-}t}$	=	50	K/W
From tab to soldering points	$R_{th\,t\text{-}s}$	=	280	K/W
From soldering points to ambient**	$R_{th\,s\text{-}a}$	=	90	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current				
$I_E = 0$; V_{CB} = 20 V	I_{CBO}	<	100	nA
$I_E = 0$; V_{CB} = 20 V; T_j = 100 °C	I_{CBO}	<	10	μA
Base emitter voltage				
I_C = 2 mA; V_{CE} = 5 V	V_{BE}	550 to 700		mV
Saturation voltages				
I_C = 10 mA; I_B = 0,5 mA	V_{CEsat}	typ.	120	mV
		<	250	mV
	V_{BEsat}	typ.	750	mV
I_C = 50 mA; I_B = 2,5 mA	V_{CEsat}	typ.	210	mV
	V_{BEsat}	typ.	850	mV

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

D.C. current gain I_C = 2 mA; V_{CE} = 5 V	h_{FE}	$>$ $<$	420 800
Collector capacitance at f = 1 MHz I_E = I_e = 0; V_{CB} = 10 V	C_c	typ.	2,5 pF ←
Transition frequency at f = 35 MHz I_C = 10 mA; V_{CE} = 5 V	f_T	typ.	300 MHz
Noise figure at R_S = 2 kΩ I_C = 200 μA; V_{CE} = 5 V f = 1 kHz; B = 200 Hz	F	$<$ typ.	4 dB 1,2 dB

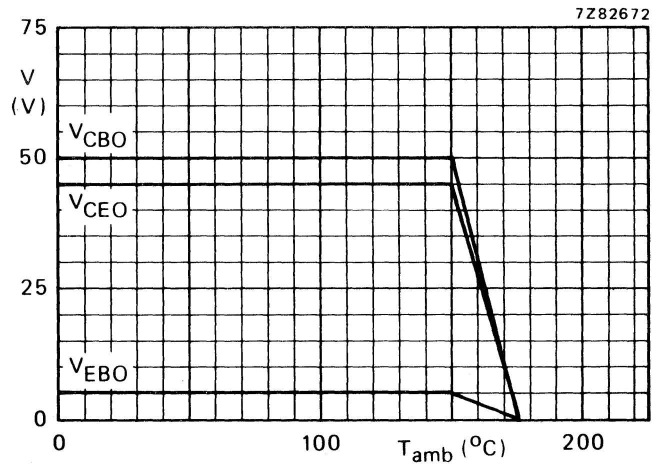


Fig. 2 Voltage derating curves.

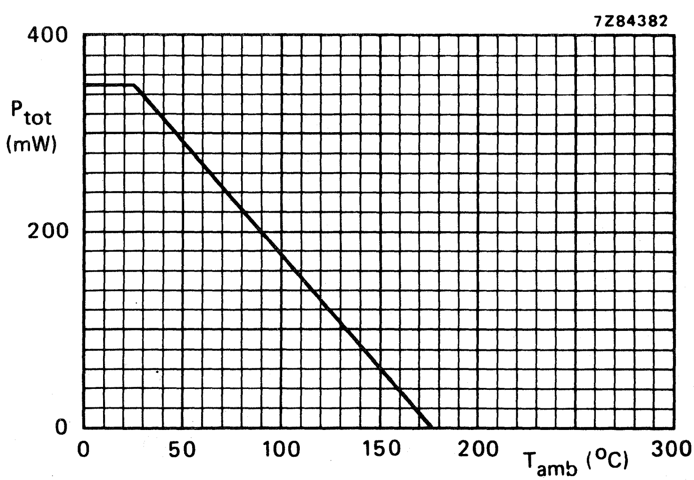


Fig. 3 Power derating curve.

SILICON PLANAR DARLINGTON TRANSISTOR

P-N-P silicon planar Darlington transistor in a plastic SOT-23 envelope.
N-P-N complement is BCV27.

QUICK REFERENCE DATA

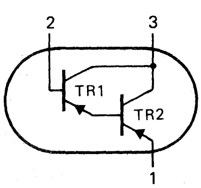
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	30 V
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	40 V
Collector current	$-I_C$	max.	300 mA
Junction temperature	T_j	max.	150 °C
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	350 mW
Collector-emitter saturation voltage $-I_C$ = 100 mA; $-I_B$ = 0,1 mA	$-V_{CEsat}$	max.	1 V
D.C. current gain $-I_C$ = 1 mA; $-V_{CE}$ = 5 V	h_{FE}	>	4 000
$-I_C$ = 10 mA; $-V_{CE}$ = 5 V	h_{FE}	>	10 000
$-I_C$ = 100 mA; $-V_{CE}$ = 5 V	h_{FE}	>	20 000
Transition frequency at f = 100 MHz $-I_C$ = 30 mA; $-V_{CE}$ = 5 V	f_T		220 MHz

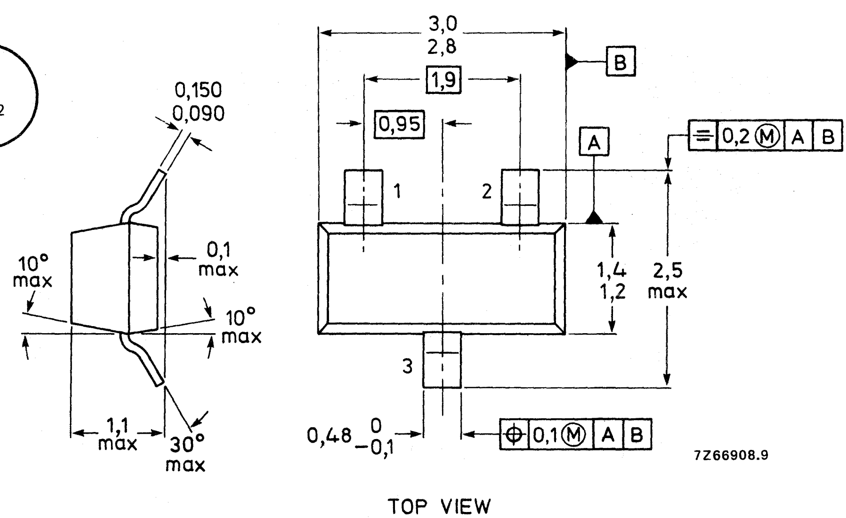
MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-23.

Marking: FD





RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-emitter voltage (open base)	$-V_{CEO}$	max.	30 V
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	40 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	10 V
Collector current	$-I_C$	max.	300 mA
Collector current (peak value)	$-I_{CM}$	max.	800 mA
Base current	$-I_B$	max.	100 mA
Total power dissipation up to T_{amb} = 25 °C*	P_{tot}	max.	350 mW
Storage temperature	T_s	−65 to + 150 °C	
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j\text{-}a}$	max.	350 K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise stated

Collector-base current $-V_{CBO}$ = 30 V	$-I_{CBO}$	max.	100 nA
Emitter-base current $-V_{EB}$ = 10 V	$-I_{EBO}$	max.	100 nA
Collector-emitter breakdown voltage $-I_C$ = 10 mA	$-V_{(BR)CEO}$	min.	30 V
Collector-base breakdown voltage $-I_C$ = 10 μA	$-V_{(BR)CBO}$	min.	40 V
Emitter-base breakdown voltage $-I_E$ = 100 nA	$-V_{(BR)EBO}$	min.	10 V
Collector-emitter saturation voltage $-I_C$ = 100 mA; $-I_B$ = 0,1 mA	$-V_{CEsat}$	max.	1 V
Base-emitter saturation voltage $-I_C$ = 100 mA; $-I_B$ = 0,1 mA	$-V_{BEsat}$	max.	1,5 V
D.C. current gain $-I_C$ = 1 mA; $-V_{CE}$ = 5 V	h_{FE}	>	4 000
$-I_C$ = 10 mA; $-V_{CE}$ = 5 V	h_{FE}	>	10 000
$-I_C$ = 100 mA; $-V_{CE}$ = 5 V	h_{FE}	>	20 000
Transition frequency at f = 100 MHz $-I_C$ = 30 mA; $-V_{CE}$ = 5 V	f_T	typ.	220 MHz
Collector capacitance at f = 1 MHz I_E = 0; $-V_{CB}$ = 30 V	C_c	typ.	3,5 pF

* Mounted on a ceramic substrate of 15 mm x 15 mm x 0,7 mm.

SILICON PLANAR DARLINGTON TRANSISTOR

N-P-N silicon planar Darlington transistor in a plastic SOT-23 envelope.
P-N-P complement is BCV26.

QUICK REFERENCE DATA

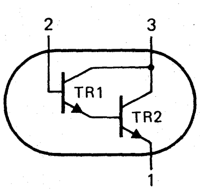
Collector-emitter voltage (open base)	V_{CEO}	max.	30	V
Collector-base voltage (open emitter)	V_{CBO}	max.	40	V
Collector current	I_C	max.	300	mA
Junction temperature	T_j	max.	150	^oC
Total power dissipation up to T_{amb} = 25 ^oC	P_{tot}	max.	350	mW
Collector-emitter saturation voltage I_C = 100 mA; I_B = 0,1 mA	V_{CEsat}	max.	1	V
D.C. current gain I_C = 1 mA; V_{CE} = 5 V	h_{FE}	>	4 000	
I_C = 10 mA; V_{CE} = 5 V	h_{FE}	>	10 000	
I_C = 100 mA; V_{CE} = 5 V	h_{FE}	>	20 000	
Transition frequency at f = 100 MHz I_C = 30 mA; V_{CE} = 5 V	f_T	typ.	220	MHz

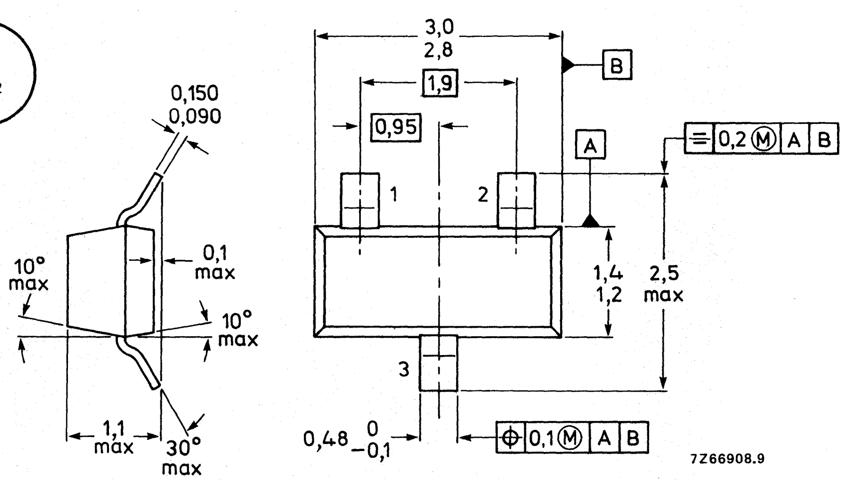
MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-23.

Marking: FF





TOP VIEW

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-emitter voltage (open base)	V_{CEO}	max.	30	V
Collector-base voltage (open emitter)	V_{CBO}	max.	40	V
Emitter-base voltage (open collector)	V_{EBO}	max.	10	V
Collector current	I_C	max.	300	mA
Collector current (peak value)	I_{CM}	max.	800	mA
Base current	I_B	max.	100	mA
Total power dissipation up to T_{amb} = 25 °C*	P_{tot}	max.	350	mW
Storage temperature	T_s	−65 to + 150		°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j\text{-}a}$	max.	350	K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise stated

Collector-base current V_{CBO} = 30 V	I_{CBO}	max.	100	nA
Emitter-base current V_{EB} = 10 V	I_{EBO}	max.	100	nA
Collector-emitter breakdown voltage I_C = 10 mA	$V_{(BR)CEO}$	min.	30	V
Collector-base breakdown voltage I_C = 10 μA	$V_{(BR)CBO}$	min.	40	V
Emitter-base breakdown voltage I_E = 100 nA	$V_{(BR)EBO}$	min.	10	V
Collector-emitter saturation voltage I_C = 100 mA; I_B = 0,1 mA	V_{CEsat}	max.	1	V
Base-emitter saturation voltage I_C = 100 mA; I_B = 0,1 mA	V_{BEsat}	max.	1,5	V
D.C. current gain I_C = 1 mA; V_{CE} = 5 V	h_{FE}	>	4 000	
I_C = 10 mA; V_{CE} = 5 V	h_{FE}	>	10 000	
I_C = 100 mA; V_{CE} = 5 V	h_{FE}	>	20 000	
Transition frequency at f = 100 MHz I_C = 30 mA; V_{CE} = 5 V	f_T	typ.	220	MHz
Collector capacitance at f = 1 MHz I_E = 0; V_{CB} = 30 V	C_c	typ.	3,5	pF

* Mounted on a ceramic substrate of 15 mm x 15 mm x 0,7 mm.

SILICON PLANAR EPITAXIAL TRANSISTOR

Double n-p-n transistor, in SOT-143 plastic envelope, designed for use in applications where the working point must be independent of temperature.

Owing to application of two similar crystals of one slice this device has a good thermal coupling and V_{BE} matching. Special interconnection of the two transistor crystals allows the device to be used as a current mirror and the separated emitter leads allow connection to different sources.

A similar device in p-n-p configuration is the BCV62.

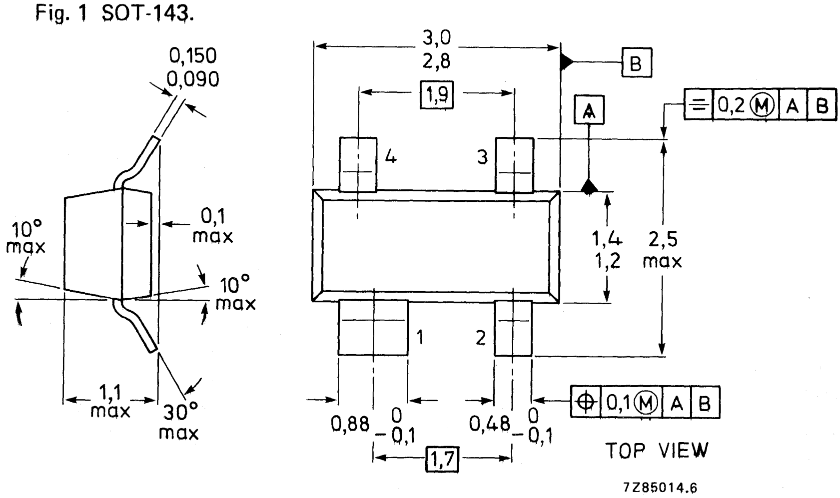
QUICK REFERENCE DATA

Collector-emitter voltage (open base) regarding transistor T1	V_{CEO}	max.	30 V
Collector-base voltage (open emitter) regarding transistor T1	V_{CBO}	max.	30 V
Collector current d.c.	I_C	max.	100 mA
peak	I_{CM}	max.	200 mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300 mW
Junction temperature	T_j	max.	150 °C

MECHANICAL DATA

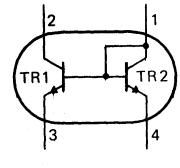
Fig. 1 SOT-143.

Dimensions in mm



Marking code:

BCV61 : D91
BCV61A: D92
BCV61B: D93
BCV61C: D94



See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-emitter voltage (open base) regarding transistor T1	V_{CEO}	max.	30 V
Collector-base voltage (open emitter) regarding transistor T1	V_{CBO}	max.	30 V
Base current (transistor T1) peak value	I_{BM1}	max.	200 mA
Emitter-base voltage	V_{EBS}	max.	6 V
Collector current d.c.	I_C	max.	100 mA
peak	I_{CM}	max.	200 mA
Total power dissipation up to T_{amb} = 25 °C when mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm	P_{tot}	max.	300 mW
Junction temperature	T_j	max.	150 °C
Storage temperature	T_{stg}		−65 to +150 °C

THERMAL RESISTANCE

Device mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm

from junction to ambient	$R_{th\ j\text{-}a}$	=	430 K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Transistor T1

Collector cut-off current			
$I_E = 0$; V_{CB} = 30 V	I_{CBO}	<	15 nA
$I_E = 0$; V_{CB} = 30 V; T_j = 150 °C	I_{CBO}	<	5 μA
Base-emitter voltage			
I_C = 2 mA; V_{CE} = 5 V	V_{BE}	typ.	660 mV*
			580 to 700 mV*
I_C = 10 mA; V_{CE} = 5 V	V_{BE}	<	770 mV*
Saturation voltages			
I_C = 10 mA; I_B = 0,5 mA	V_{CEsat}	typ.	90 mV
		<	250 mV
	V_{BEsat}	typ.	700 mV**
I_C = 100 mA; I_B = 5 mA	V_{CEsat}	typ.	200 mV
		<	600 mV
	V_{BEsat}	typ.	900 mV**

* Decreasing 2 mV/°C with increasing temperature.

** Decreasing 1,7 mV/°C with increasing temperature.

Transition frequency at f = 35 MHz			
I_C = 10 mA; V_{CE} = 5 V		f_T	typ. 300 MHz
Collector capacitance at f = 1 MHz			
$I_E = i_e = 0$; V_{CB} = 10 V		C_c	typ. 2,5 pF
Noise figure at R_S = 2 kΩ			
I_C = 200 μA; V_{CE} = 5 V		F	typ. 2 dB
f = 1 kHz; B = 200 Hz			< 10 dB
D.C. current gain			
I_C = 100 μA; V_{CE} = 5 V		h_{FE}	> 100
I_C = 2 mA; V_{CE} = 5 V		h_{FE}	110 to 800
Input impedance			
I_C = 2 mA; V_{CE} = 5 V; f = 1 kHz		h_{ie}	typ. 5 kΩ
Reverse voltage transfer ratio			
I_C = 2 mA; V_{CE} = 5 V; f = 1 kHz		h_{re}	typ. 2×10^{-4}
Small signal current gain			
I_C = 2 mA; V_{CE} = 5 V; f = 1 kHz		h_{fe}	100 to 900
Output admittance			
I_C = 2 mA; V_{CE} = 5 V; f = 1 kHz		h_{oe}	typ. 30 μS

Transistor T2

Base-emitter forward voltage			
I_E = 250 mA		V_{BES}	< 1,8 V
I_E = 10 μA		V_{BES}	> 400 mV
Matching of transistor T1 and transistor T2			
at I_{E2} = 0,5 mA and V_{CE1} = 5 V			
T_{amb} = 25 °C		I_{C1}/I_{C2}	0,7 to 1,3
T_{amb} = 150 °C		I_{C1}/I_{C2}	0,7 to 1,3
Thermal coupling of transistor T1 and Transistor T2*			
T1 : V_{CE} = 5 V			
Maximum current for thermal stability of I_{C1}		I_{E2}	typ. 5 mA
D.C. current gain			min. 110
I_C = 2 mA; V_{CE} = 5 V	BCV61A	h_{FE}	typ. 180
			max. 220
			min. 200
	BCV61B	h_{FE}	typ. 290
			max. 450
			min. 420
	BCV61C	h_{FE}	typ. 520
			max. 800

* Without emitter resistor and device mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm. (See Fig. 2)

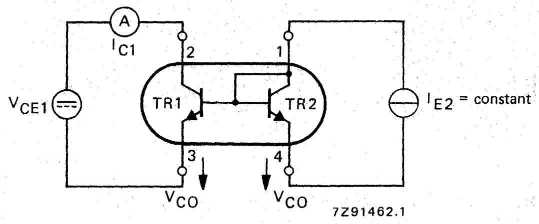


Fig. 2 Test circuit current matching.

Note: Voltage drop at contacts: $V_{co} < \frac{2}{3} U_T \triangleq 16$ mV.

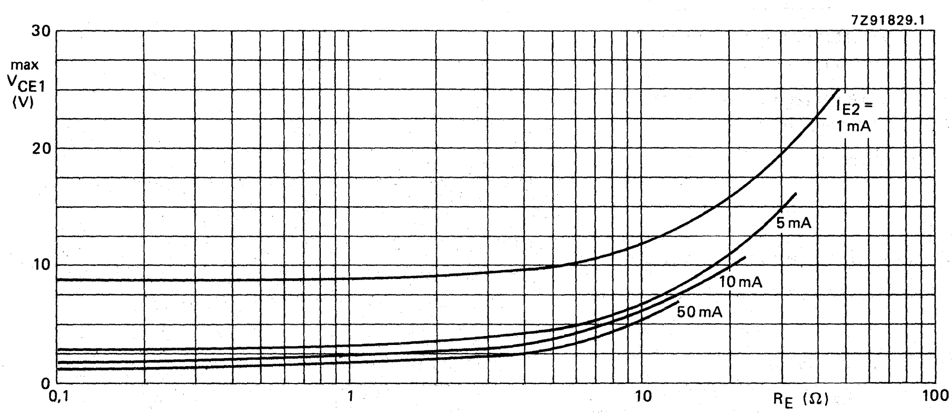


Fig. 3 Characteristic for determination of max. V_{CE1} at specified R_E range with I_{E2} as parameter under condition of $\frac{I_{C1}}{I_{E2}} = 1{,}3$ (see Fig. 4).

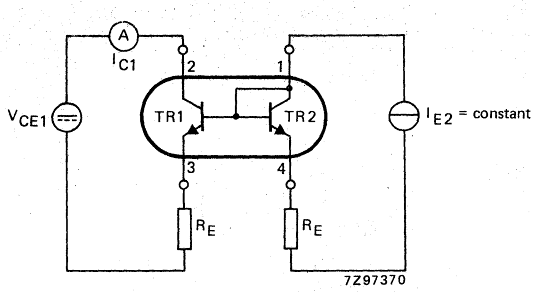


Fig. 4 BCV61 with emitter resistors.

SILICON PLANAR EPITAXIAL TRANSISTOR

Double p-n-p transistor, in SOT-143 plastic envelope, designed for use in applications where the working point must be independent of temperature.

Owing to application of two similar crystals of one slice this device has a good thermal coupling and V_{BE} matching. Special interconnection of the two transistor crystals allows the device to be used as a current mirror and the separated emitter leads allow connection to different sources.

A similar device in n-p-n configuration is the BCV61.

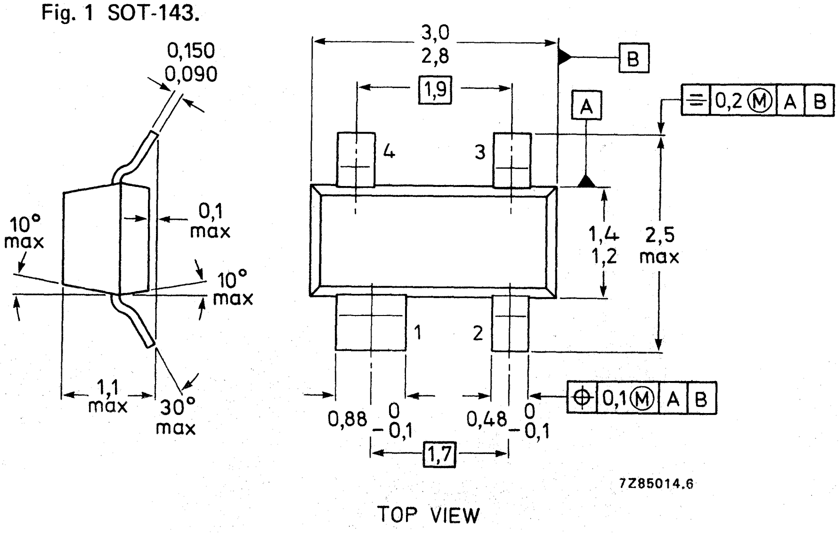
QUICK REFERENCE DATA

Collector-emitter voltage (open base) regarding transistor T1	$-V_{CEO}$	max	30 V
Collector-base voltage (open emitter) regarding transistor T1	$-V_{CBO}$	max.	30 V
Collector current d.c.	$-I_C$	max.	100 mA
peak	$-I_{CM}$	max.	200 mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300 mW
Junction temperature	T_j	max.	150 °C

MECHANICAL DATA

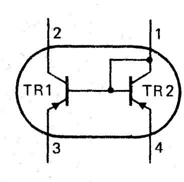
Fig. 1 SOT-143.

Dimensions in mm



Marking code:

BCV62 : C91
BCV62A: C92
BCV62B: C93
BCV62C: C94



See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-emitter voltage (open base) regarding transistor T1	$-V_{CEO}$	max.	30	V
Collector-base voltage (open emitter) regarding transistor T1	$-V_{CBO}$	max.	30	V
Base current (transistor T1) peak value	$-I_{BM1}$	max.	200	mA
Emitter-base voltage	$-V_{EBS}$	max.	6	V
Collector current d.c.	$-I_C$	max.	100	mA
peak	$-I_{CM}$	max.	200	mA
Total power dissipation up to T_{amb} = 25 °C when mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm	P_{tot}	max.	300	mW
Junction temperature	T_j	max.	150	°C
Storage temperature	T_{stg}		−65 to +150	°C

THERMAL RESISTANCE

Device mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm

from junction to ambient	$R_{th\ j\text{-}a}$	=	430	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Transistor T1

Collector cut-off current				
$-I_E = 0$; $-V_{CB} = 30$ V	$-I_{CBO}$	<	15	nA
$-I_E = 0$; $-V_{CB} = 30$ V; $T_j = 150$ °C	$-I_{CBO}$	<	5	μA
Base-emitter voltage				
$-I_C = 2$ mA; $-V_{CE} = 5$ V	$-V_{BE}$	typ.	650	mV*
			600 to 750	mV*
$-I_C = 10$ mA; $-V_{CE} = 5$ V	$-V_{BE}$	<	820	mV*
Saturation voltages				
$-I_C = 10$ mA; $-I_B = 0{,}5$ mA	$-V_{CEsat}$	typ.	75	mV
		<	300	mV
	$-V_{BEsat}$	typ.	700	mV**
$-I_C = 100$ mA; $-I_B = 5$ mA	$-V_{CEsat}$	typ.	250	mV
		<	650	mV
	$-V_{BEsat}$	typ.	850	mV**

* Decreasing 2 mV/°C with increasing temperature.
** Decreasing 1,7 mV/°C with increasing temperature.

Transition frequency at f = 35 MHz			
$-I_C$ = 10 mA; $-V_{CE}$ = 5 V	f_T	typ.	150 MHz
Collector capacitance at f = 1 MHz			
$I_E = i_e = 0$; $-V_{CB}$ = 10 V	C_c	typ.	4,5 pF
Noise figure at R_S = 2 kΩ			
$-I_C$ = 200 μA; $-V_{CE}$ = 5 V	F	typ.	2 dB
f = 1 kHz; B = 200 Hz		<	10 dB
D.C. current gain			
$-I_C$ = 100 μA; $-V_{CE}$ = 5 V	h_{FE}	>	100
$-I_C$ = 2 mA; $-V_{CE}$ = 5 V	h_{FE}		100 to 800
Input impedance			
$-I_C$ = 2 mA; $-V_{CE}$ = 5 V; f = 1 kHz	h_{ie}	typ.	3 kΩ
Reverse voltage transfer ratio			
$-I_C$ = 2 mA; $-V_{CE}$ = 5 V; f = 1 kHz	h_{re}	typ.	3×10^{-4}
Small signal current gain			
$-I_C$ = 2 mA; $-V_{CE}$ = 5 V; f = 1 kHz	h_{fe}		100 to 900
Output admittance			
$-I_C$ = 2 mA; $-V_{CE}$ = 5 V; f = 1 kHz	h_{oe}	typ.	50 μS

Transistor T2

Base-emitter forward voltage				
$-I_E$ = 250 mA		$-V_{BES}$	<	1,5 V
$-I_E$ = 10 μA		$-V_{BES}$	>	400 mV
Matching of transistor T1 and transistor T2 at I_{E2} = 0,5 mA and V_{CE1} = 5 V				
T_{amb} = 25 °C		I_{C1}/I_{C2}	0,7 to 1,3	
T_{amb} = 150 °C		I_{C1}/I_{C2}	0,7 to 1,3	
Thermal coupling of transistor T1 and transistor T2* T1 : $-V_{CE}$ = 5 V Maximum current for thermal stability of $-I_{C1}$		I_{E2}	typ.	5 mA
D.C. current gain	BCV62A	h_{FE}	min.	125
			typ.	180
			max.	250
	BCV62B	h_{FE}	min.	220
			typ.	290
			max.	475
	BCV62C	h_{FE}	min.	420
			typ.	520
			max.	800

* Without emitter resistor and device mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm. (see Fig. 2)

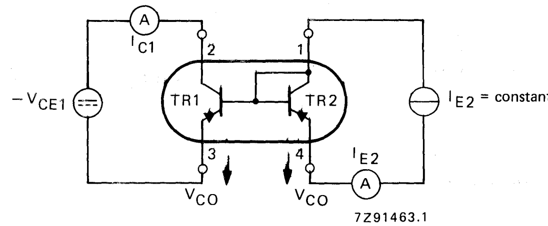


Fig. 2 Test circuit current matching.

Note: Voltage drop at contacts: $V_{co} < \frac{2}{3} U_T \triangleq 16$ mV.

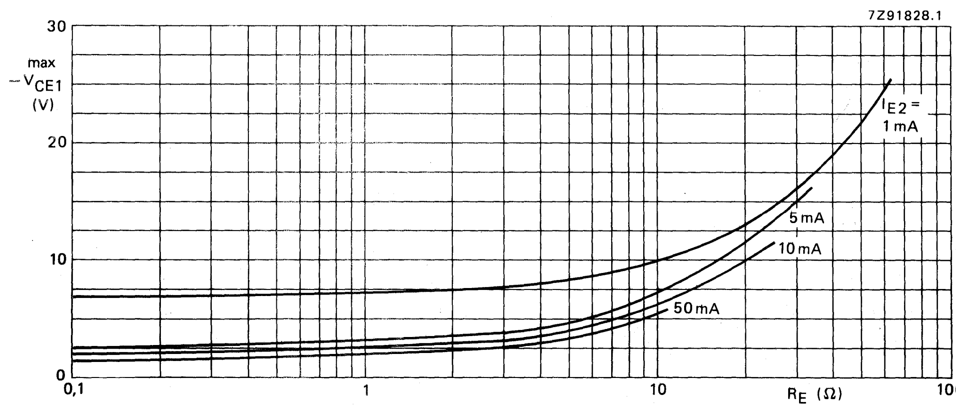


Fig. 3 Characteristic for determination of max. V_{CE1} at specified R_E range with I_{E2} as parameter under condition of $\frac{I_{C1}}{I_{E2}} = 1{,}3$ (see Fig. 4).

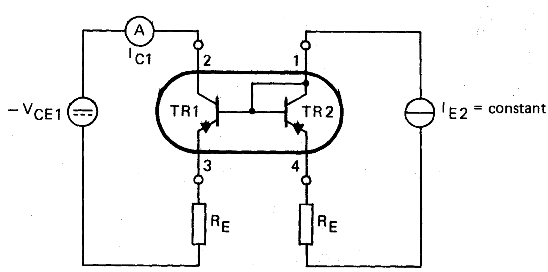


Fig. 4 BCV62 with emitter resistors.

SILICON PLANAR TRANSISTOR

Double N-P-N transistor in a plastic SOT-143 envelope. Intended for Schmitt-trigger applications. P-N-P complement is the BCV64.

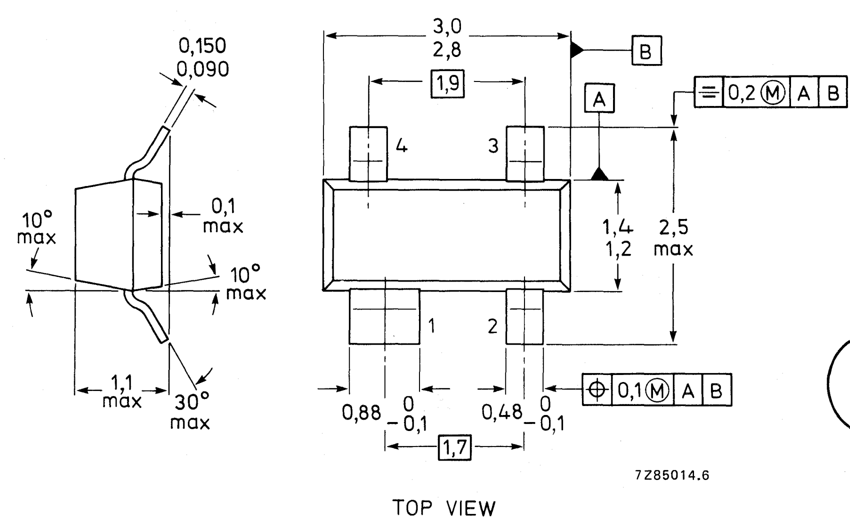
QUICK REFERENCE DATA

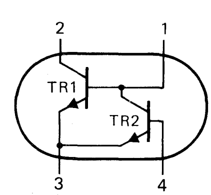
	transistor		T1	T2	
Collector-emitter voltage (open base)	V_{CEO}	max.	30	6	V
Collector-base voltage (open emitter)	V_{CBO}	max.	30	6	V
Collector current	I_C	max.	100		mA
Junction temperature	T_j	max.	150		^oC
Total power dissipation up to T_{amb} = 25 ^oC	P_{tot}	max.	300		mW
Collector-emitter saturation voltage I_C = 10 mA; I_B = 0,5 mA	V_{CEsat}	max.	300		mV
Small signal current gain	h_{fe}		100 to 900		
Transition frequency at f = 35 MHz I_C = 10 mA; V_{CE} = 5 V	f_T	typ.	200	–	MHz

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-143.





RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

	transistor		T1	T2	
Collector-emitter voltage (open base)	V_{CEO}	max.	30	6	V
Collector-base voltage (open emitter)	V_{CBO}	max.	30	6	V
Emitter-base voltage (open collector)	V_{EBO}	max.	6		V
Collector current (d.c.)	I_C	max.	100		mA
Collector current (peak value)	I_{CM}	max.	200		mA
Total power dissipation up to T_{amb} = 25 °C*	P_{tot}	max.	300		mW
Storage temperature	T_s		−65 to +150		°C
Junction temperature	T_j	max.	150		°C

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j\text{-}a}$	max.	430	K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise stated

	transistor		T1	T2	
Collector cut-off current					
I_E = 0; V_{CBO} = 30 V	I_{CBO}	max.	15	15	nA
I_E = 0; V_{CBO} = 30 V; T_j = 150 °C	I_{CBO}	max.	5	5	μA
Saturation voltage**					
I_C = 10 mA; I_B = 0,5 mA	V_{CEsat}	typ.	75	75	mV
	V_{CEsat}	max.	300	300	mV
	V_{BEsat}	typ.	700	700	mV
I_C = 100 mA; I_B = 5 mA	V_{CEsat}	typ.	250	250	mV
	V_{CEsat}	max.	650	–	mV
	V_{BEsat}	typ.	850	–	mV
Base-emitter voltage ▲					
I_C = 2 mA; V_{CE} = 5 V	V_{BE}	min.	600	–	mV
	V_{BE}	typ.	650	–	mV
	V_{BE}	max.	750	–	mV
I_C = 10 mA; V_{CE} = 5 V	V_{BE}	max.	820	–	mV
I_C = 2 mA; V_{CE} = 700 mV	V_{BE}	typ.		700	mV
Collector capacitance at f = 1 MHz					
I_E = i_e = 0; V_{CE} = 10 V	C_c	typ.	4	–	pF
Transition frequency at f = 35 MHz					
I_C = 10 mA; V_{CE} = 5 V	f_T	typ.	200	–	MHz

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

** V_{BEsat} decreases by approx 1,7 mV/K with increasing temperature.

▲ $-V_{BE}$ decreases by about 2 mV/K with increasing temperature.

Small signal current gain at f = 1 kHz
I_C = 2 mA; T1 : V_{CE} = 5 V
T2 : V_{CE} = 700 mV — h_{fe} — 100 to 900

Transistor 1

D.C. current gain

I_C = 2 mA; V_{CE} = 5 V

	BCV	63	A	B	C
h_{FE}	min.	110	110	200	420
	typ.		180	290	520
	max.	800	220	450	800

Transistor 2

D.C. current gain
I_C = 2 mA; V_{CE} = 700 mV

Group selection will be done on T1. Due to matched crystals h_{FE} values for T2 are the same as T1.

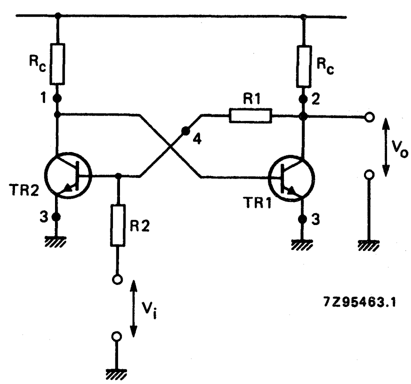


Fig. 2 Schmitt-trigger application.

DEVELOPMENT DATA

SILICON PLANAR TRANSISTOR

Double P-N-P transistor in a plastic SOT-143 envelope. Intended for Schmitt-trigger applications. N-P-N complement is the BCV63.

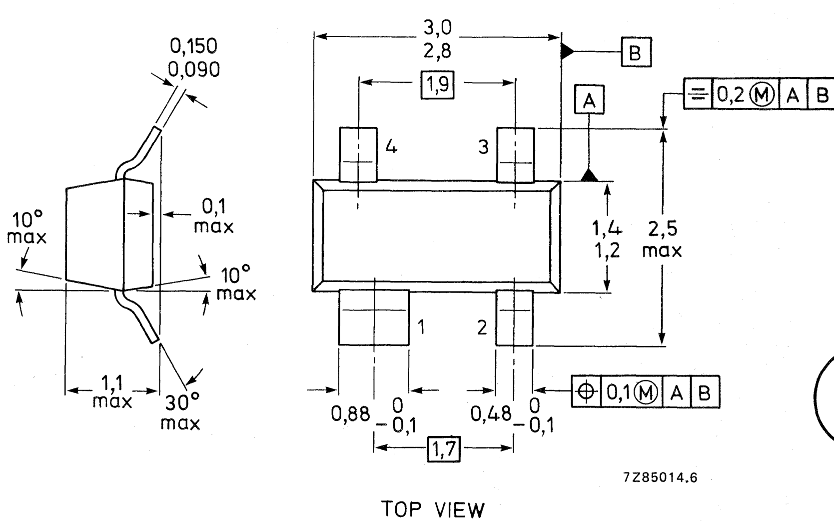
QUICK REFERENCE DATA

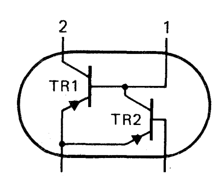
	transistor		T1	T2	
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	30	6	V
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	30	6	V
Collector current	$-I_C$	max.	100		mA
Junction temperature	T_j	max.	150		°C
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300		mW
Collector-emitter saturation voltage $-I_C$ = 10 mA; $-I_B$ = 0,5 mA	$-V_{CEsat}$	max.	300		mV
Small signal current gain	h_{fe}		100 to 900		
Transition frequency at f = 35 MHz $-I_C$ = 10 mA; $-V_{CE}$ = 5 V	f_T	typ.	200	–	MHz

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-143.





RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			transistor T1	T2	
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	30	6	V
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	30	6	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	6	6	V
Collector current (d.c.)	$-I_C$	max.	6		mA
Collector current (peak value)	$-I_{CM}$	max.	200		mA
Total power dissipation up to T_{amb} = 25 °C*	P_{tot}	max.	300		mW
Storage temperature	T_s		−65 to +150		°C
Junction temperature	T_j	max.	150		°C

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j\text{-}a}$	max.	430	K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise stated

			transistor T1	T2	
Collector cut-off current					
$-I_E = 0$; $-V_{CBO}$ = 30 V	$-I_{CBO}$	max.	15	15	nA
$-I_E = 0$; $-V_{CBO}$ = 30 V; T_j = 150 °C	$-I_{CBO}$	max.	5	5	μA
Saturation voltage**					
$-I_C$ = 10 mA; $-I_B$ = 0,5 mA	$-V_{CEsat}$	typ.	75	75	mV
	$-V_{CEsat}$	max.	300	300	mV
	$-V_{BEsat}$	typ.	700	700	mV
$-I_C$ = 100 mA; $-I_B$ = 5 mA	$-V_{CEsat}$	typ.	250	250	mV
	$-V_{CEsat}$	max.	650	−	mV
	$-V_{BEsat}$	typ.	850	−	mV
Base-emitter voltage ▲					
$-I_C$ = 2 mA; $-V_{CE}$ = 5 V	$-V_{BE}$	typ.	650	−	mV
			600/750	−	mV
$-I_C$ = 10 mA; $-V_{CE}$ = 5 V	$-V_{BE}$	max.	820	−	mV
$-I_C$ = 2 mA; $-V_{CE}$ = 700 mV	$-V_{BE}$	typ.		700	mV
Collector capacitance at f = 1 MHz					
$-I_E = i_e = 0$; $-V_{CE}$ = 10 V	C_c	typ.	4	−	pF
Transition frequency at f = 35 MHz					
$-I_C$ = 10 mA; $-V_{CE}$ = 5 V	f_T	typ.	200	−	MHz

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

** V_{BEsat} decreases by approx 1,7 mV/K with increasing temperature.

▲ $-V_{BE}$ decreases by about 2 mV/K with increasing temperature.

Small signal current gain at f = 1 kHz
$-I_C$ = 2 mA; T1 : $-V_{CE}$ = 5 V
T2 : $-V_{CE}$ = 700 mV — h_{fe} — 100 to 900

Transistor 1

D.C. current gain
$-I_C$ = 2 mA; $-V_{CE}$ = 5 V

		BCV	64	A	B	C
		min.	110	125	220	420
	h_{FE}	typ.		180	290	520
		max.	800	250	475	800

Transistor 2

D.C. current gain
$-I_C$ = 2 mA; $-V_{CE}$ = 700 mV

Group selection will be done on T1. Due to matched crystals h_{FE} values for T2 are the same as T1.

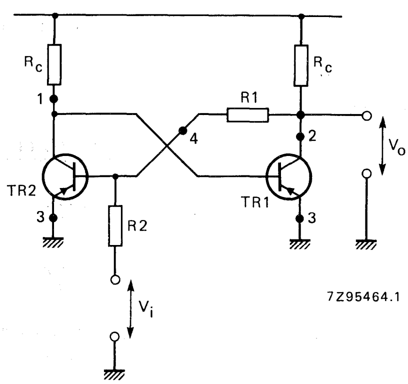


Fig. 2 Schmitt-trigger application.

DEVELOPMENT DATA

SILICON PLANAR TRANSISTORS

A pair of two matched P-N-P and N-P-N crystals, based on the BC857 and BC847, in a microminiature SOT-143 envelope.

Complementary crystals give advantages in P.C.B. layout using S.M.D. technology.

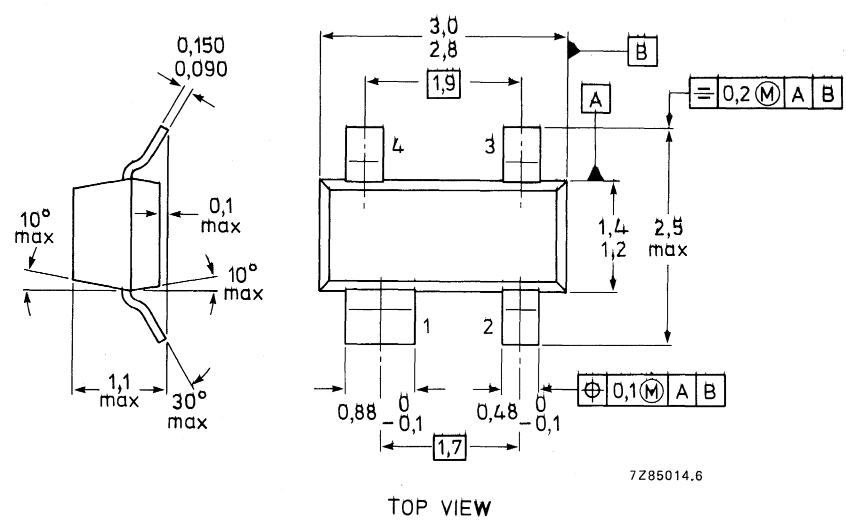
QUICK REFERENCE DATA

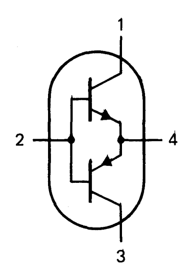
Collector-emitter voltage (open base)	V_{CEO}	max.	30 V
Collector-base voltage (open emitter)	V_{CBO}	max.	30 V
Collector current	I_C	max.	100 mA
Collector current (peak value)	I_{CM}	max.	200 mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300 mW
Junction temperature	T_j	max.	150 °C

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-143.





RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Per transistor:

Collector-emitter voltage (open base)	V_{CEO}	max.	30 V
Collector-base voltage (open emitter)	V_{CBO}	max.	30 V
Collector current	I_C	max.	100 mA
Collector current (peak value)	I_{CM}	max.	200 mA
Total power dissipation (per device) up to T_{amb} = 25 °C	P_{tot}	max.	300 mW
Storage temperature	T_s		−65 to + 150 °C
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j\text{-}a}$	max.	430 K/W

CHARACTERISTICS

Per transistor:

T_j = 25 °C unless otherwise stated

Collector cut-off current			
I_E = 0; V_{CB} = 30 V	I_{CBO}	max.	15 nA
I_E = 0; V_{CB} = 30 V; T_j = 150 °C	I_{CBO}	max.	5 μA
Base-emitter voltage**			
I_C = 2 mA; V_{CE} = 5 V	V_{BE}	typ.	650 mV
			580 to 750 mV
I_C = 10 mA; V_{CE} = 5 V	V_{BE}	max.	820 mV
Saturation voltage▲			
I_C = 10 mA; I_B = 0,5 mA	V_{CEsat}	typ.	90 mV
		max.	300 mV
	V_{BEsat}	typ.	700 mV
I_C = 100 mA; I_B = 5 mA	V_{CEsat}	typ.	250 mV
		max.	650 mV
	V_{BEsat}	typ.	900 mV
Collector capacitance at f = 1 MHz			
$I_E = i_e$ = 0; V_{CE} = 10 V	C_c	typ.	3 pF

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

** V_{BEsat} decreases by approx. 1,7 mV/K with increasing temperature.

▲ $-V_{BE}$ decreases by about 2 mV/K with increasing temperature.

Transition frequency at f = 35 MHz I_C = 10 mA; V_{CE} = 5 V		f_T	min.	100 MHz
Noise figure at f = 35 MHz I_C = 200 μA; V_{CE} = 5 V; f = 1 kHz; B = 200 Hz		F	typ. max.	2 dB 10 dB
Small signal current gain at f = 1 kHz I_C = 2 mA; V_{CE} = 5 V		h_{fe}		75 to 900
D.C. current gain I_C = 2 mA; V_{CE} = 5 V	BCV65	h_{FE}	min. max.	75 800
	BCV65B	h_{FE}	min. typ. max.	200 290 475

DEVELOPMENT DATA

SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N transistors, in a microminiature plastic envelope, intended for low level general purpose applications in thick and thin-film circuits.

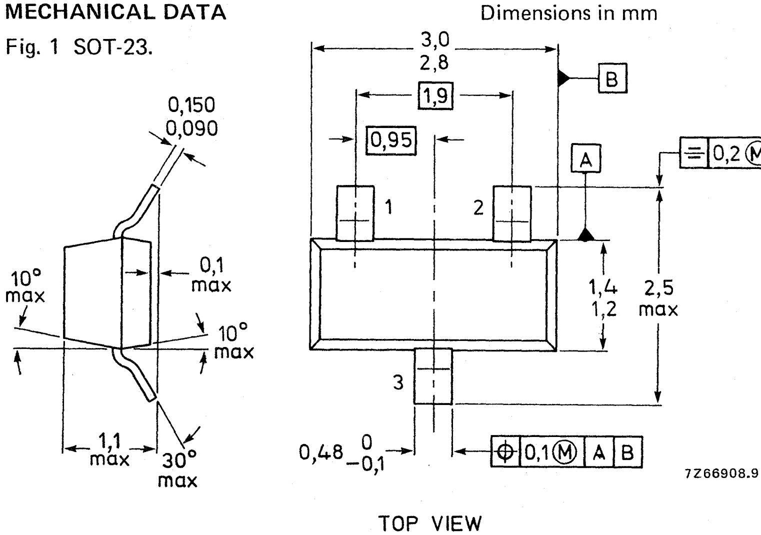
QUICK REFERENCE DATA

			BCV71	BCV72	
D.C. current gain at T_j = 25 °C; I_C = 2 mA; V_{CE} = 5 V	h_{FE}	>	110	200	
		<	220	450	
Collector-base voltage (open emitter)	V_{CBO}	max.	80		V
Collector-emitter voltage (open base)	V_{CEO}	max.	60		V
Collector current (peak value)	I_{CM}	max.	200		mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	350		mW
Junction temperature	T_j	max.	175		°C
Transition frequency at f = 35 MHz; I_C = 10 mA; V_{CE} = 5 V	f_T	typ.	300		MHz
Noise figure at R_S = 2 kΩ; I_C = 200 μA; V_{CE} = 5 V; f = 1 kHz; B = 200 Hz	F	<	10		dB

MECHANICAL DATA

Dimensions in mm

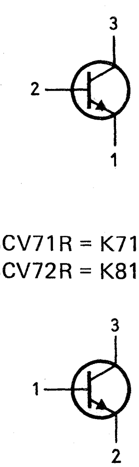
Fig. 1 SOT-23.



Marking code

BCV71 = K7
BCV72 = K8

BCV71R = K71
BCV72R = K81



R-types are available on request

See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter) see Fig. 2	V_{CBO}	max.	80	V
Collector-emitter voltage (open base) see Fig. 2 $I_C = 2$ mA	V_{CEO}	max.	60	V
Emitter-base voltage (open collector) see Fig. 2	V_{EBO}	max.	5	V
Collector current (d.c.)	I_C	max.	100	mA
Collector current (peak value)	I_{CM}	max.	200	mA
Total power dissipation up to $T_{amb} = 25\ ^oC$**	P_{tot}	max.	350	mW
Storage temperature	T_{stg}	−65 to + 175		^oC
Junction temperature	T_j	max.	175	^oC

THERMAL CHARACTERISTICS*

$T_j = Px\,(R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	50	K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280	K/W
From soldering points to ambient**	$R_{th\ s\text{-}a}$	=	90	K/W

CHARACTERISTICS

$T_j = 25\ ^oC$ unless otherwise specified

Collector cut-off current				
$I_E = 0$; $V_{CB} = 20$ V	I_{CBO}	<	100	nA
$I_E = 0$; $V_{CB} = 20$ V; $T_j = 100\ ^oC$	I_{CBO}	<	10	μA
Base emitter voltage				
$I_C = 2$ mA; $V_{CE} = 5$ V	V_{BE}	550 to 700		mV
Saturation voltages				
$I_C = 10$ mA; $I_B = 0,5$ mA	V_{CEsat}	typ.	120	mV
		<	250	mV
	V_{BEsat}	typ.	750	mV
$I_C = 50$ mA; $I_B = 2,5$ mA	V_{CEsat}	typ.	210	mV
	V_{BEsat}	typ.	850	mV

* See *Thermal characteristics.*
** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

			BCV71	BCV72	
D.C. current gain					
$I_C = 10\ \mu A$; $V_{CE} = 5$ V	h_{FE}	typ.	90	150	
$I_C = 2$ mA; $V_{CE} = 5$ V	h_{FE}	>	110	200	
		<	220	450	
Collector capacitance at f = 1 MHz					
$I_E = I_e = 0$; $V_{CB} = 10$ V	C_c	typ.	2,5		pF ←
Transition frequency at f = 35 MHz					
$I_C = 10$ mA; $V_{CE} = 5$ V	f_T	typ.	300		MHz
Noise figure at $R_S = 2\ k\Omega$					
$I_C = 200\ \mu A$; $V_{CE} = 5$ V					
f = 1 kHz; B = 200 Hz	F	<	10		dB

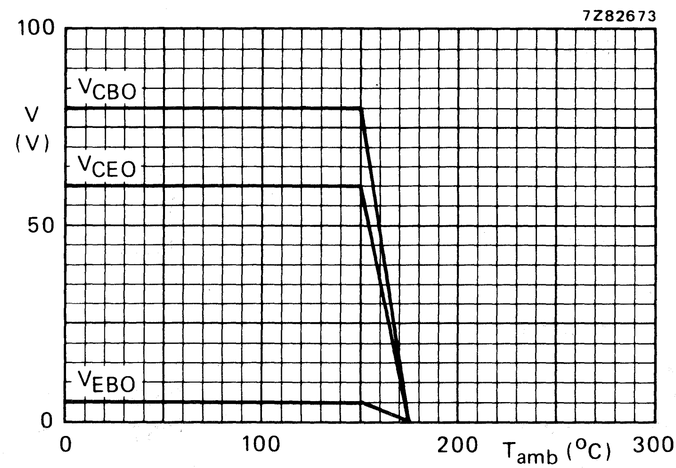


Fig. 2 Voltage derating curves.

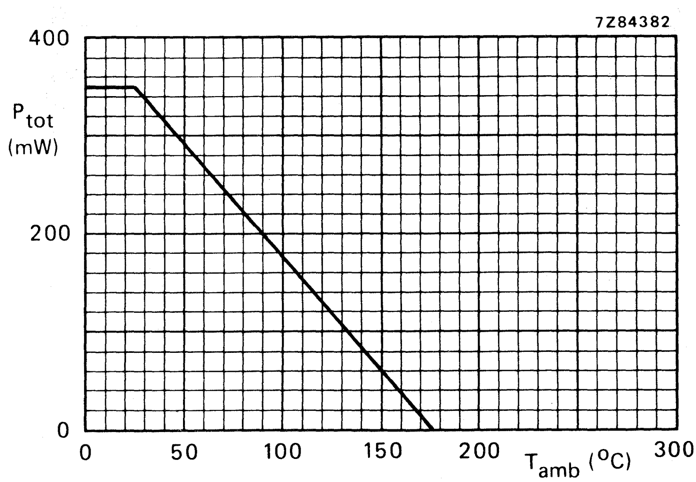


Fig. 3 Power derating curve.

SILICON PLANAR EPITAXIAL TRANSISTORS

P-N-P transistors, in a microminiature plastic envelope, intended for low level general purpose applications in thick and thin-film circuits.

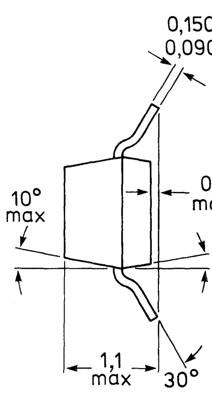
QUICK REFERENCE DATA

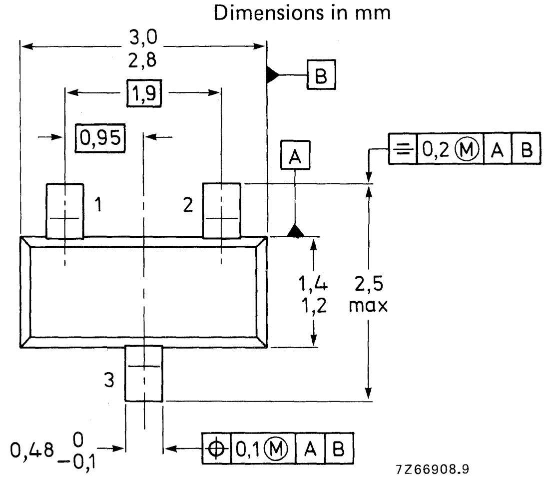
			BCW29	BCW30	
D.C. current gain at T_j = 25 °C $-I_C$ = 2 mA; $-V_{CE}$ = 5 V	h_{FE}	>	120	215	
		<	260	500	
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	32		V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	32		V
Collector current (peak value)	$-I_{CM}$	max.	200		mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	350		mW
Junction temperature	T_j	max.	175		°C
Transition frequency at f = 35 MHz $-I_C$ = 10 mA; $-V_{CE}$ = 5 V	f_T	typ.	150		MHz
Noise figure at R_S = 2 kΩ $-I_C$ = 200 µA; $-V_{CE}$ = 5 V; f = 1 kHz; B = 200 Hz	F	<	10		dB

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-23.

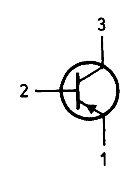




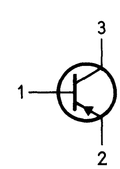
TOP VIEW

Marking code

BCW29 = C1
BCW30 = C2



BCW29R = C4
BCW30R = C5



R-types are available on request

See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC134)

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	32 V
Collector-emitter voltage (V_{BE} = 0)	$-V_{CES}$	max.	32 V
Collector-emitter voltage (open base) $-I_C$ = 2 mA	$-V_{CEO}$	max.	32 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5 V
Collector current (d.c.)	$-I_C$	max.	100 mA
Collector current (peak value)	$-I_{CM}$	max.	200 mA
Total power dissipation up to T_{amb} = 25 °C**	P_{tot}	max.	350 mW
Storage temperature	T_{stg}		−65 to +175 °C
Junction temperature	T_j	max.	175 °C

THERMAL CHARACTERISTICS*

$T_j = P \times (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	50 K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280 K/W
From soldering points to ambient**	$R_{th\ s\text{-}a}$	=	90 K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current			
$I_E = 0$; $-V_{CB}$ = 32 V	$-I_{CBO}$	<	100 nA
$I_E = 0$; $-V_{CB}$ = 32 V; T_j = 100 °C	$-I_{CBO}$	<	10 μA
Base-emitter voltage			
$-I_C$ = 2 mA; $-V_{CE}$ = 5 V	$-V_{BE}$		600 to 750 mV
Saturation voltages			
$-I_C$ = 10 mA; $-I_B$ = 0,5 mA	$-V_{CEsat}$	typ.	80 mV
		<	300 mV
	$-V_{BEsat}$	typ.	720 mV
$-I_C$ = 50 mA; $-I_B$ = 2,5 mA	$-V_{CEsat}$	typ.	150 mV
	$-V_{BEsat}$	typ.	810 mV

* See *Thermal characteristics.*
** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

			BCW29	BCW30	
D.C. current gain					
$-I_C = 10\ \mu A$; $-V_{CE} = 5\ V$	h_{FE}	typ.	90	150	
$-I_C = 2\ mA$; $-V_{CE} = 5\ V$	h_{FE}	>	120	215	
		<	260	500	
Collector-capacitance at f = 1 MHz $I_E = I_e = 0$; $-V_{CB} = 10\ V$	C_c	typ.	4,5		pF ←
Transition frequency at f = 35 MHz $-I_C = 10\ mA$; $-V_{CE} = 5\ V$	f_T	typ.	150		MHz
Noise figure at $R_S = 2\ k\Omega$ $-I_C = 200\ \mu A$; $-V_{CE} = 5\ V$ f = 1 kHz; B = 200 Hz	F	<	10		dB

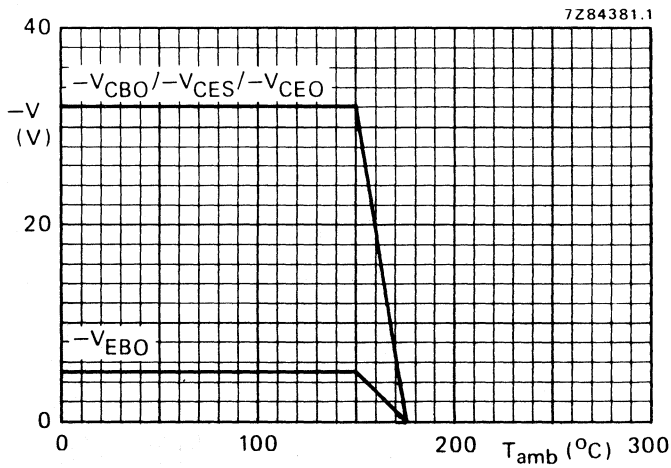


Fig. 2 Voltage derating curves.

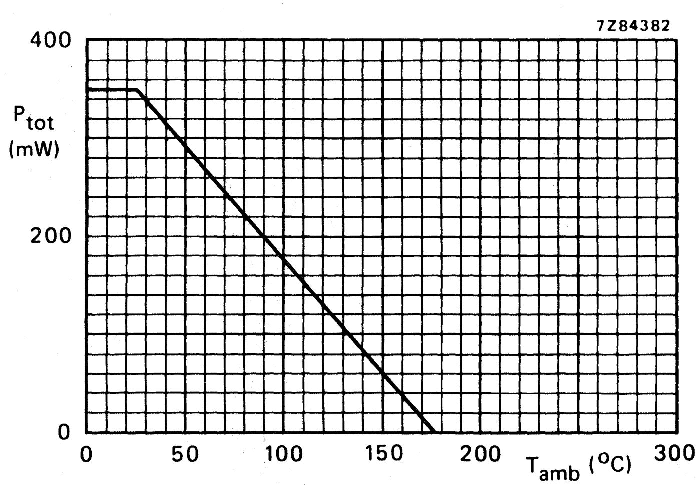


Fig. 3 Power derating curve.

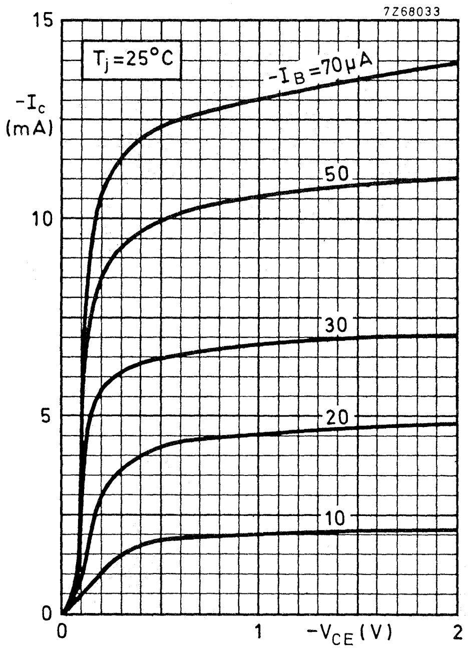


Fig. 4.

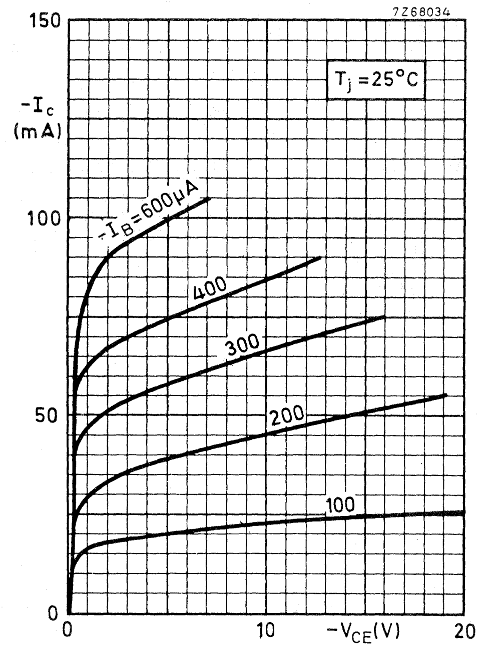


Fig. 5.

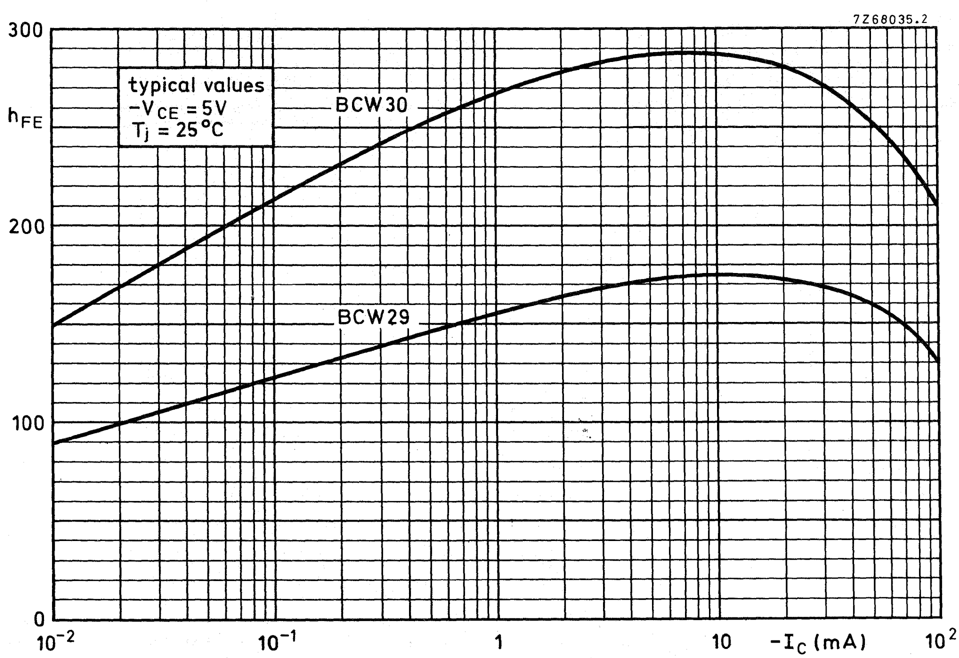


Fig. 6.

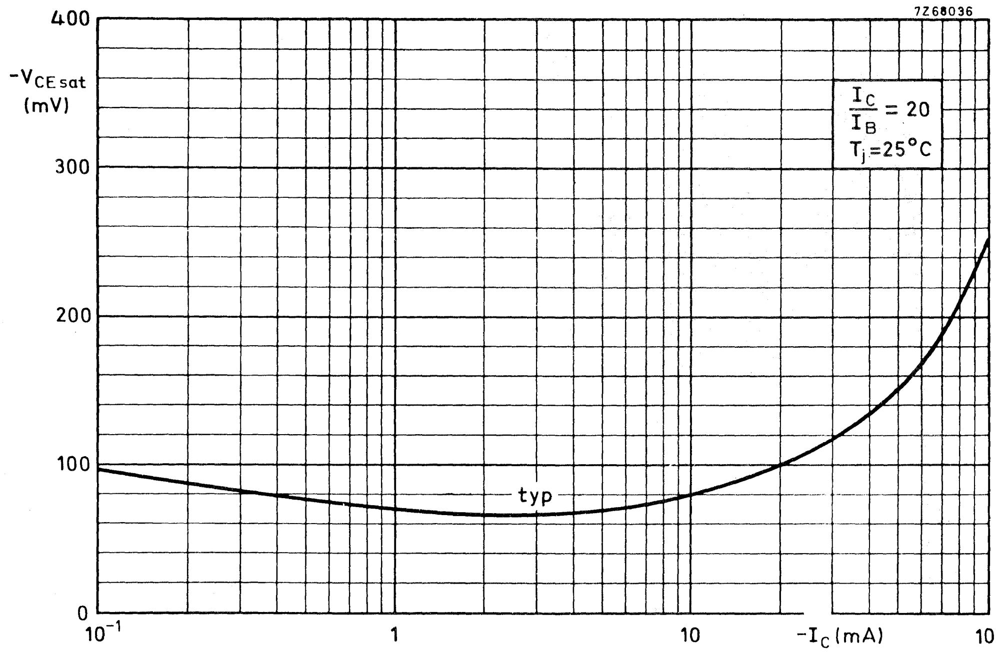

7Z68036
400
300
200
100
0
$-V_{CE\,sat}$ (mV)
$\frac{I_C}{I_B} = 20$
$T_j = 25\,°C$
typ
10^{-1}
1
10
$-I_C$ (mA)
10^2

Fig. 7.

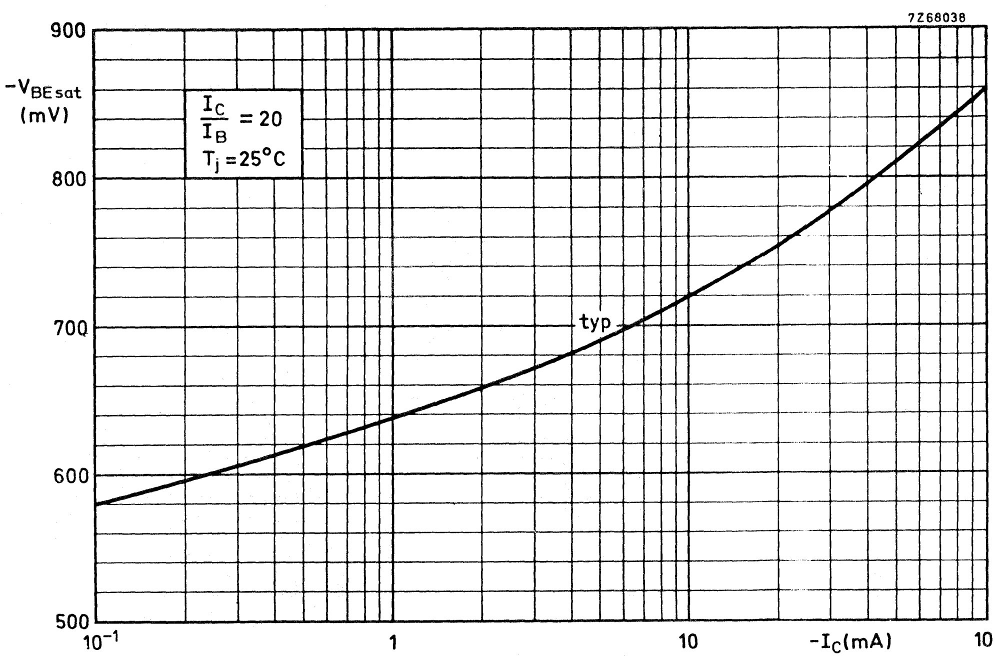

7Z68038
900
800
700
600
500
$-V_{BE\,sat}$ (mV)
$\frac{I_C}{I_B} = 20$
$T_j = 25\,°C$
typ
10^{-1}
1
10
$-I_C$ (mA)
10^2

Fig. 8.

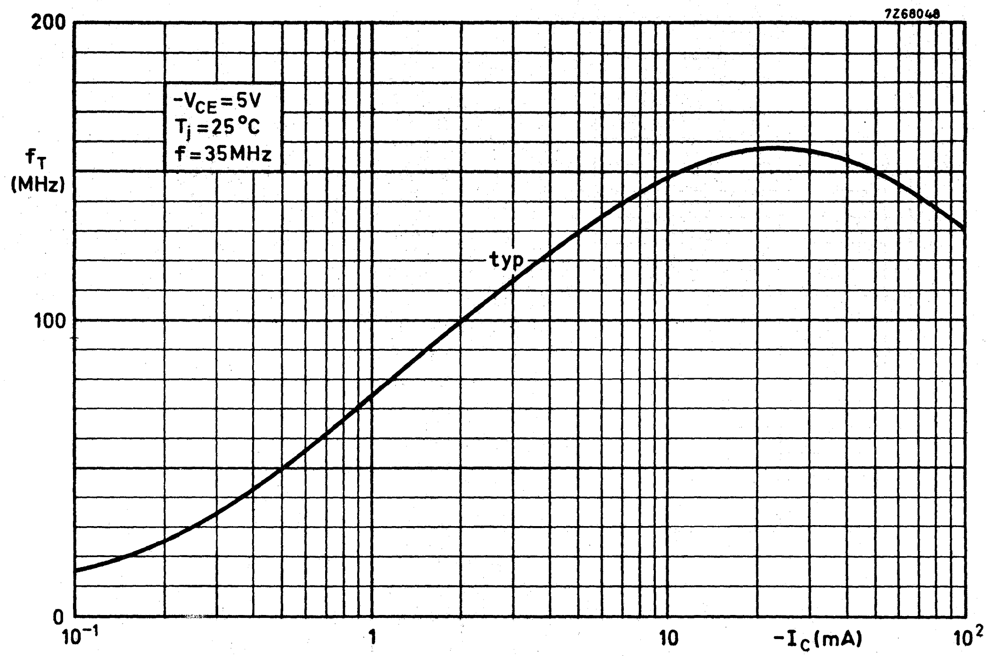


Fig. 9.

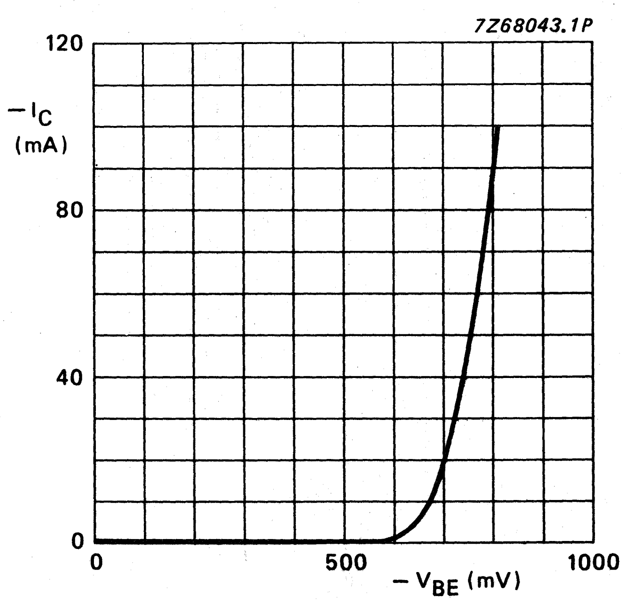


Fig. 10 V_{CE} = 5 V; T_j = 25 °C; typical values.

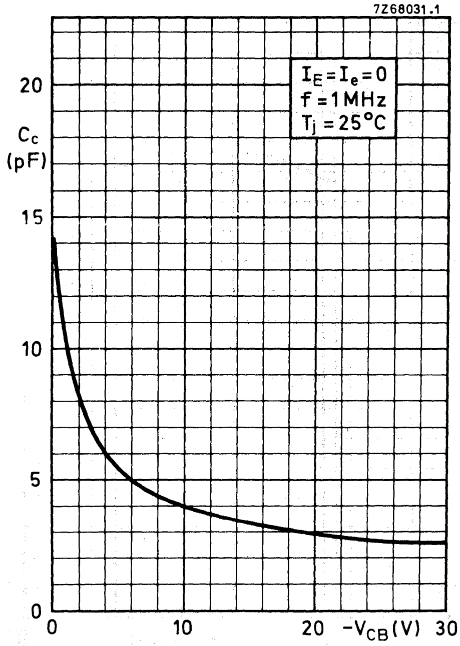

7Z68031.1
$I_E = I_e = 0$
f = 1 MHz
$T_j = 25\,°C$
C_c (pF)
20
15
10
5
0
0
10
20
$-V_{CB}$ (V)
30

Fig. 11.

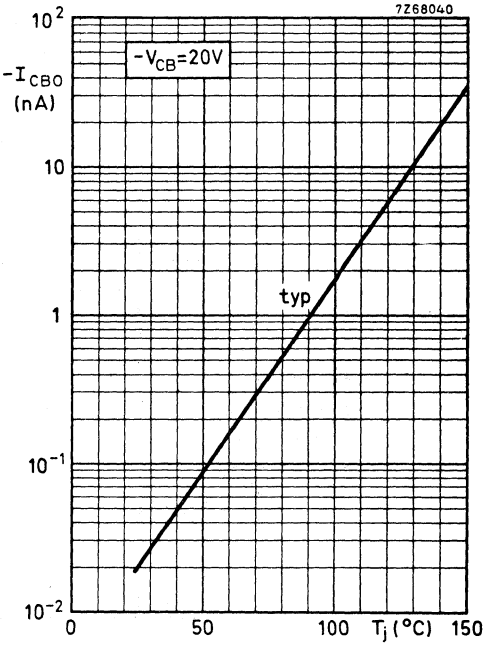

7Z68040
$-V_{CB} = 20\,V$
$-I_{CBO}$ (nA)
10^2
10
1
10^{-1}
10^{-2}
typ
0
50
100
T_j (°C)
150

Fig. 12.

SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N transistors in a microminiature plastic envelope. They are intended for low level general purpose applications in thick and thin-film circuits.

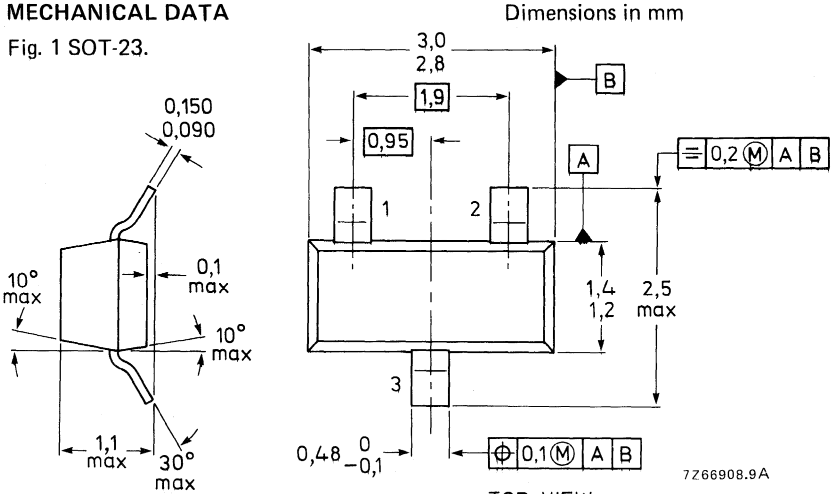
QUICK REFERENCE DATA

			BCW31	BCW32	BCW33	
D.C. current gain at T_j = 25 °C I_C = 2 mA; V_{CE} = 5 V	h_{FE}	>	110	200	420	
		<	220	450	800	
Collector-base voltage (open emitter)	V_{CBO}	max.		32		V
Collector-emitter voltage (open base)	V_{CEO}	max.		32		V
Collector current (peak value)	I_{CM}	max.		200		mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.		350		mW
Junction temperature	T_j	max.		175		°C
Transition frequency at f = 35 MHz I_C = 2 mA; V_{CE} = 5 V	f_T	typ.		300		MHz
Noise figure at R_S = 2 kΩ I_C = 200 μA; V_{CE} = 5 V; f = 1 kHz; B = 200 Hz	F	<		10		dB

MECHANICAL DATA

Dimensions in mm

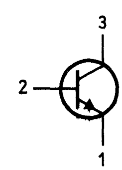
Fig. 1 SOT-23.



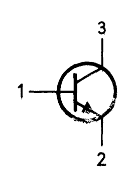
TOP VIEW

Marking code

BCW31 = D1
BCW32 = D2
BCW33 = D3



BCW31R = D4
BCW32R = D5
BCW33R = D6 ←



R-types are available on request.

See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC134)

Collector-base voltage (open emitter)	V_{CBO}	max.	32 V
Collector-emitter voltage (open base) $I_C = 2$ mA	V_{CEO}	max.	32 V
Emitter-base voltage (open collector)	V_{EBO}	max.	5 V
Collector current (d.c.)	I_C	max.	100 mA
Collector current (peak value)	I_{CM}	max.	200 mA
Total power dissipation up to $T_{amb} = 25\ ^oC$**	P_{tot}	max.	350 mW
Storage temperature	T_{stg}		−65 to +175 ^oC
Junction temperature	T_j	max.	175 ^oC

THERMAL CHARACTERISTICS*

$$T_j = P \times (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	50 K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280 K/W
From soldering points to ambient**	$R_{th\ s\text{-}a}$	=	90 K/W

CHARACTERISTICS

$T_j = 25\ ^oC$ unless otherwise specified

Collector cut-off current			
$I_E = 0$; $V_{CB} = 32$ V	I_{CBO}	<	100 nA
$I_E = 0$; $V_{CB} = 32$ V; $T_j = 100\ ^oC$	I_{CBO}	<	10 μA
Base-emitter voltage			
$I_C = 2$ mA; $V_{CE} = 5$ V	V_{BE}		550 to 700 mV
Saturation voltages			
I_C 10 mA; $I_B = 0{,}5$ mA	V_{CEsat}	typ.	120 mV
		<	250 mV
	V_{BEsat}	typ.	750 mV
$I_C = 50$ mA; $I_B = 2{,}5$ mA	V_{CEsat}	typ.	210 mV
	V_{BEsat}	typ.	850 mV

* See *Thermal characteristics.*
** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

			BCW31	BCW32	BCW33	
D.C. current gain						
I_C = 10 μA, V_{CE} = 5 V	h_{FE}	typ.	90	150	270	
I_C = 2 mA; V_{CE} = 5 V	h_{FE}	>	110	200	420	
		<	220	450	800	
Collector capacitance at f = 1 MHz $I_E = I_e = 0$; V_{CB} = 10 V	C_c	typ.		2,5		pF ←
Transition frequency at f = 35 MHz I_C = 10 mA; V_{CE} = 5 V	f_T	typ.		300		MHz
Noise figure at R_S = 2 kΩ I_C = 200 μA; V_{CE} = 5 V f = 1 kHz; B = 200 Hz	F	<		10		dB

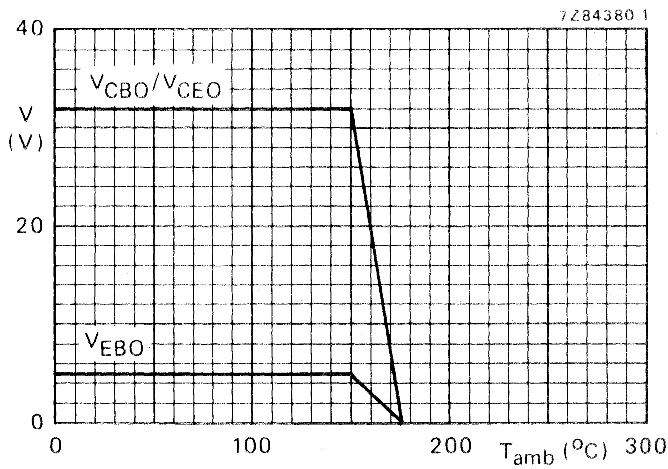


Fig. 2 Voltage derating curves.

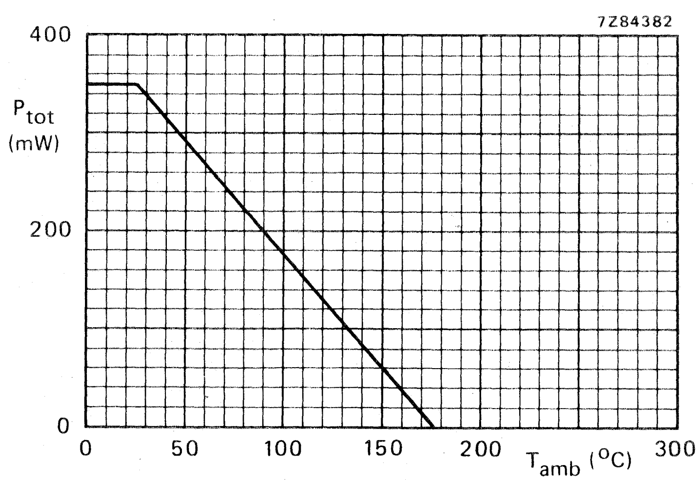


Fig. 3 Power derating curve.

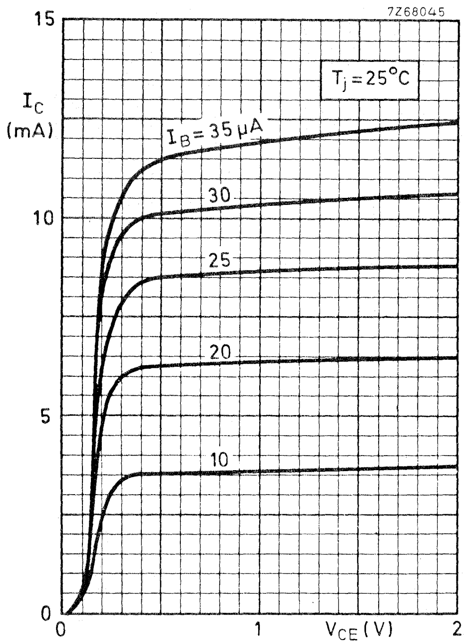


Fig. 4.

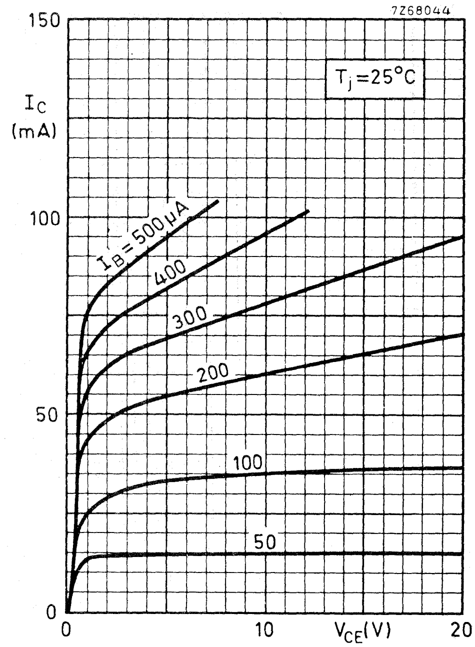


Fig. 5.

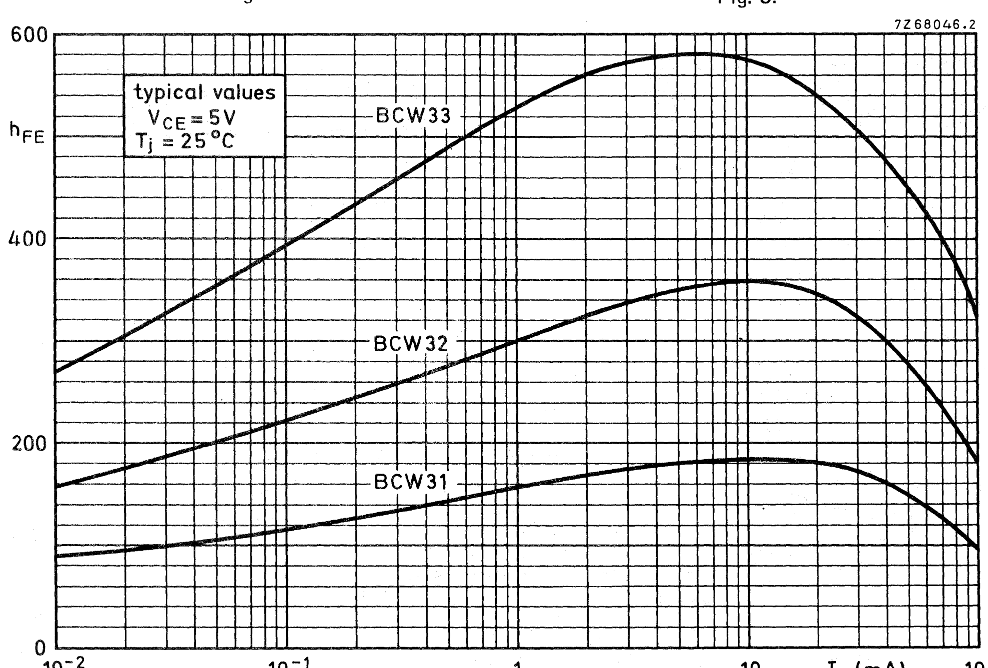


Fig. 6.

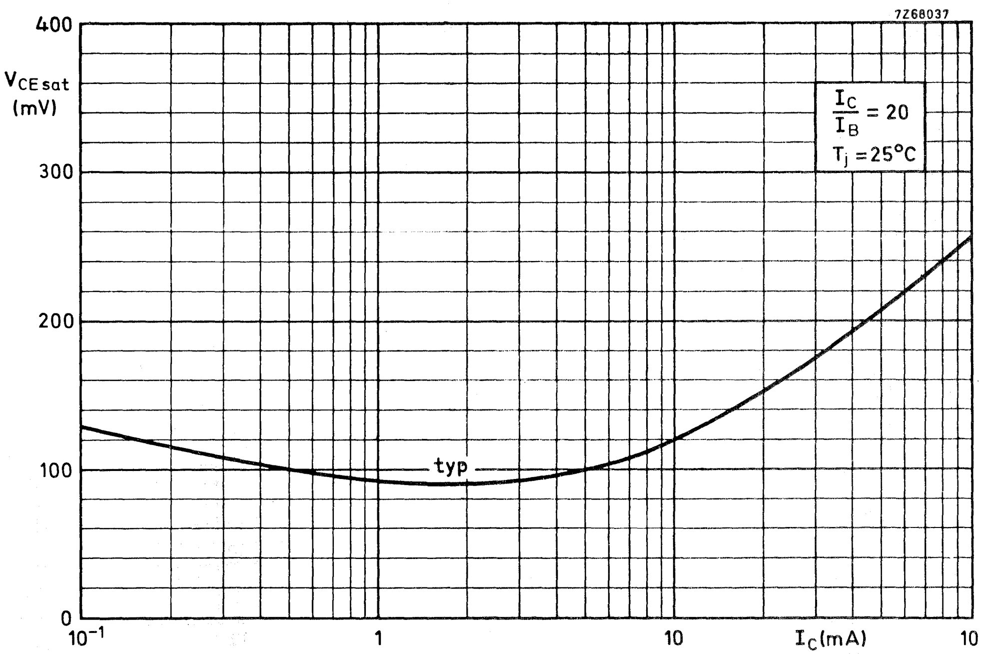

7Z68037
400
300
200
100
0
V_{CEsat}
(mV)
$\frac{I_C}{I_B} = 20$
$T_j = 25^\circ C$
typ
10^{-1}
1
10
I_C(mA)
10^2

Fig. 7.

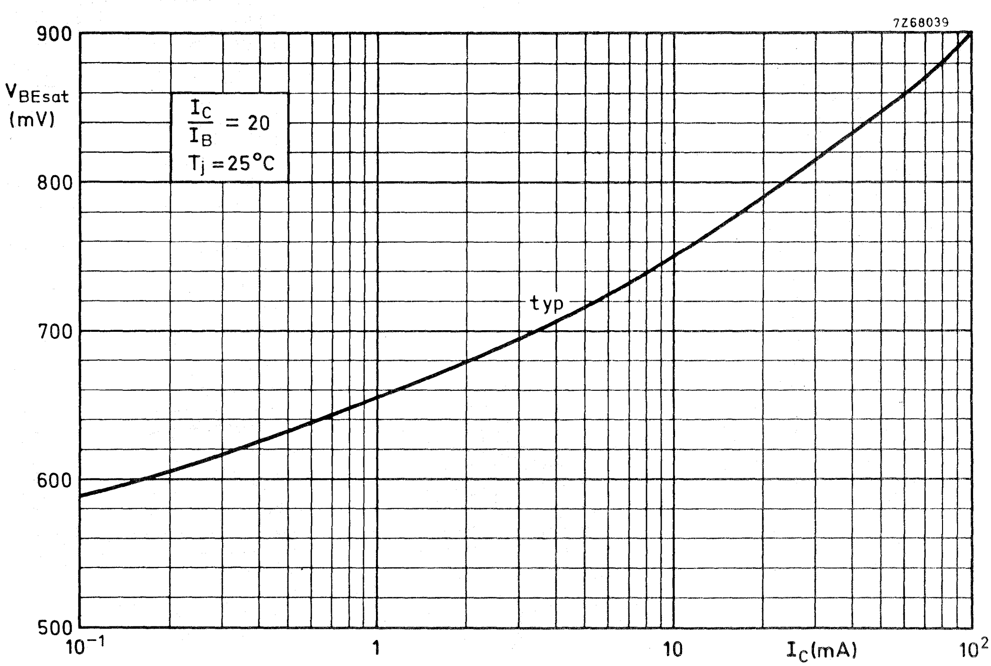

7Z68039
900
800
700
600
500
V_{BEsat}
(mV)
$\frac{I_C}{I_B} = 20$
$T_j = 25^\circ C$
typ
10^{-1}
1
10
I_C(mA)
10^2

Fig. 8.

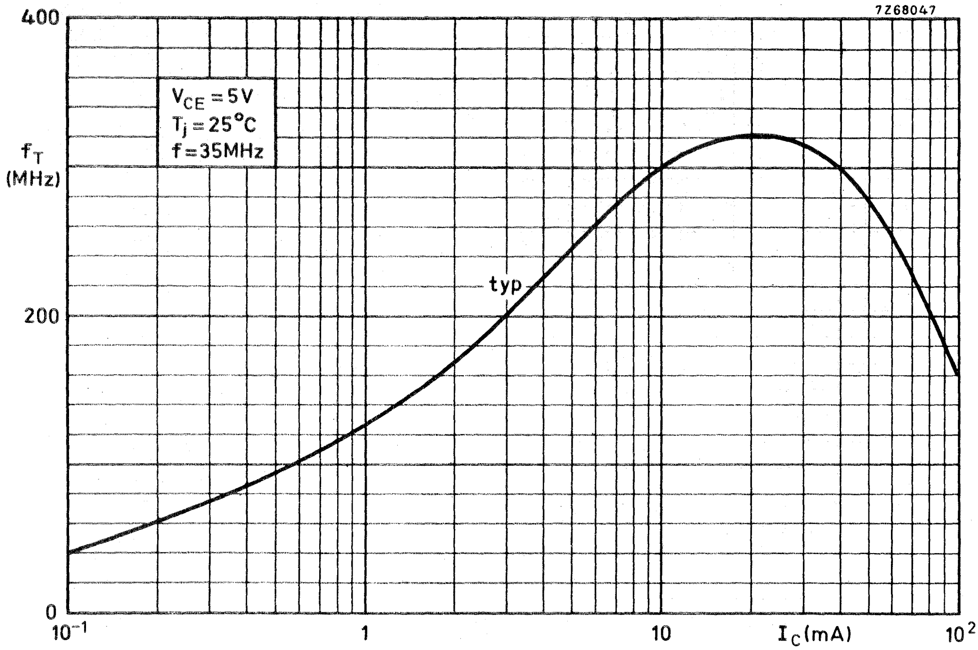


Fig. 9.

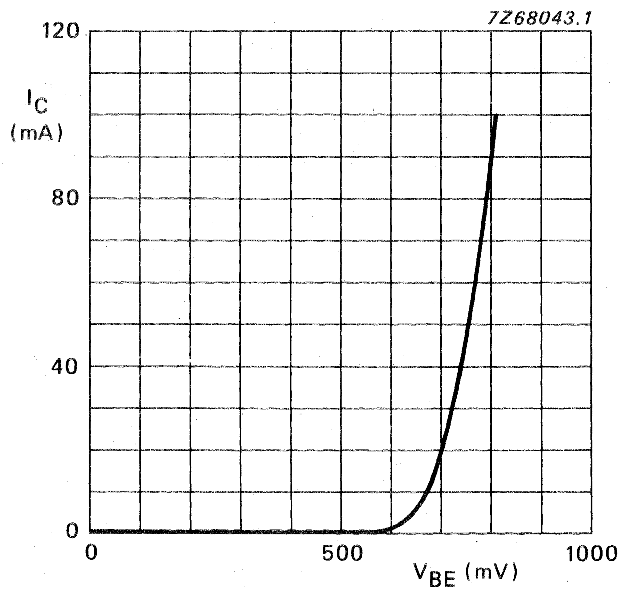


Fig. 10 V_{CE} = 5 V; T_j = 25 °C; typical values.

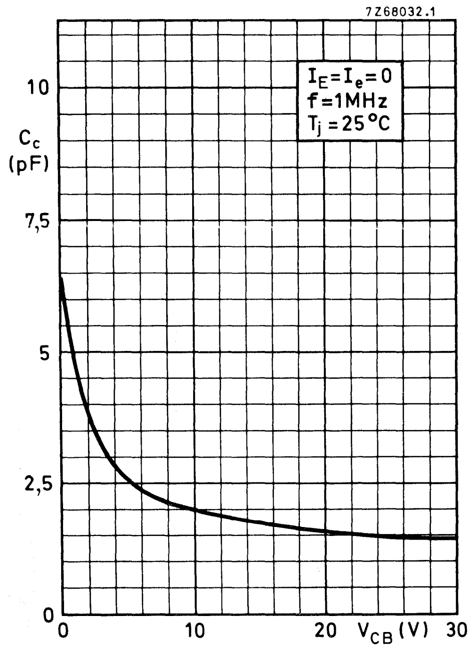

7Z68032.1
$I_E = I_e = 0$
f = 1 MHz
$T_j = 25\ ^\circ C$
C_c (pF)
10
7,5
5
2,5
0
0
10
20
V_{CB} (V)
30

Fig. 11.

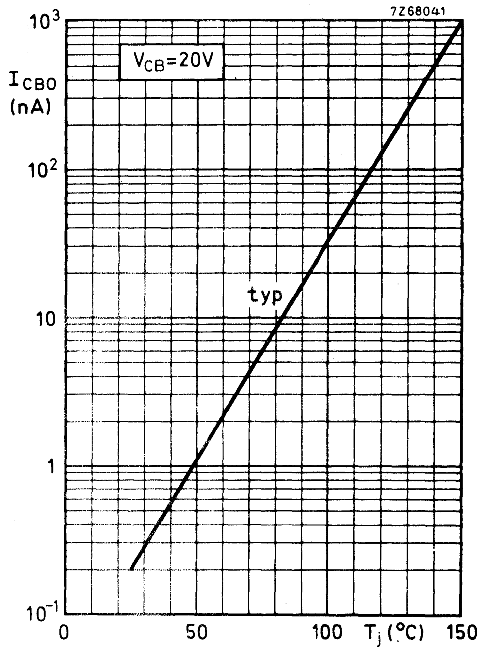

7Z68041
$V_{CB} = 20V$
I_{CBO} (nA)
10^3
10^2
10
1
10^{-1}
typ
0
50
100
T_j (°C)
150

Fig. 12.

SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N silicon transistors, in a microminiature plastic envelope, intended for low level, low noise, low frequency purpose applications in hybrid circuits.

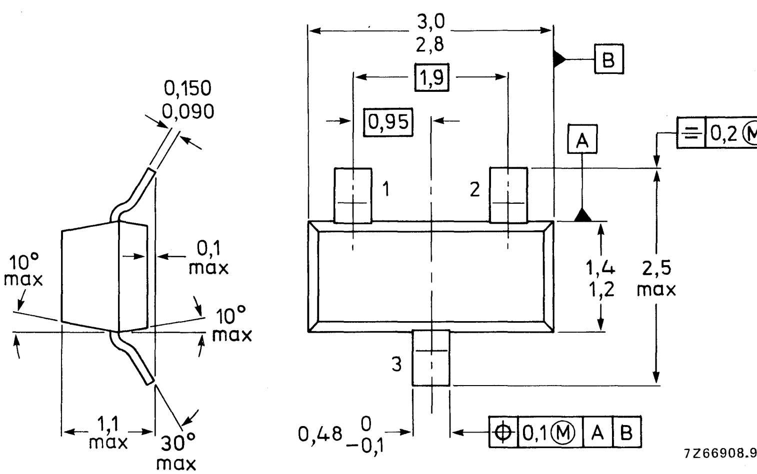
QUICK REFERENCE DATA

Collector-emitter voltage (V_{BE} = 0)	V_{CES}	max.	32	V
Collector-emitter voltage (open base)	V_{CEO}	max.	32	V
Collector current (d.c.)	I_C	max.	200	mA
Total power dissipation	P_{tot}	max.	150	mW
Junction temperature	T_j	max.	150	^oC
Transition frequency at f = 100 MHz V_{CE} = 5 V; I_C = 10 mA	f_T	typ.	250	MHz
Noise figure at f = 1 kHz V_{CE} = 5 V; I_C = 200 μA; B = 200 Hz	F	typ.	2	dB

MECHANICAL DATA

Dimensions in mm

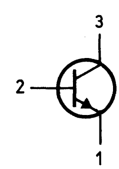
Fig. 1 SOT-23.



TOP VIEW

Marking code

BCW60A = AA
BCW60B = AB
BCW60C = AC
BCW60D = AD



See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-emitter voltage (V_{BE} = 0)	V_{CES}	max.	32	V
Collector-emitter voltage (open base)	V_{CEO}	max.	32	V
Emitter-base voltage (open collector)	V_{EBO}	max.	5	V
Collector current (d.c.)	I_C	max.	200	mA
Base current	I_B	max.	50	mA
Total power dissipation up to T_{amb} = 100 °C**	P_{tot}	max.	150	mW
Storage temperature	T_{stg}	−55 to + 125		°C
Junction temperature	T_j	max.	150	°C

THERMAL CHARACTERISTICS*

$T_j = P \times (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	50	K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280	K/W
From soldering points to ambient**	$R_{th\ s\text{-}a}$	=	90	K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Collector-emitter cut-off current				
V_{BE} = 0; V_{CE} = 32 V	I_{CES}	<	20	nA
V_{BE} = 0; V_{CE} = 32 V; T_{amb} = 150 °C	I_{CES}	<	20	μA
Emitter-base cut-off current				
I_C = 0; V_{EB} = 4 V	I_{EBO}	<	20	nA
Saturation voltages				
at I_C = 10 mA; I_B = 0,25 mA	V_{CEsat}	0,05 to 0,35		V
	V_{BEsat}	0,6 to 0,85		V
at I_C = 50 mA; I_B = 1,25 mA	V_{CEsat}	0,1 to 0,55		V
	V_{BEsat}	0,7 to 1,05		V
Transition frequency at f = 100 MHz ▲				
I_C = 10 mA; V_{CE} = 5 V	f_T	>	125	MHz
		typ.	250	MHz
Collector capacitance at f = 1 MHz				
→ I_E = I_e = 0; V_{CB} = 10 V	C_c	typ.	2,5	pF
Emitter capacitance at f = 1 MHz				
I_C = I_c = 0; V_{EB} = 0,5 V	C_e	typ.	8	pF
Noise figure at R_S = 2 kΩ				
I_C = 200 μA; V_{CE} = 5 V; f = 1 kHz; B = 200 Hz	F	typ.	2	dB
		<	6	dB

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

▲ Measured under pulse conditions.

			A	B	C	D		
D.C. current gain								
V_{CE} = 5 V; I_C = 10 μA	h_{FE}	typ.	78	145	220	300		
		>	–	20	40	100		
V_{CE} = 5 V; I_C = 2 mA	h_{FE}	>	120	180	250	380		
		typ.	170	250	350	500		
		<	220	310	460	630		
V_{CE} = 1 V; I_C = 50 mA	h_{FE}	>	50	70	90	100		
Input impedance								
V_{CE} = 5 V; I_C = 2 mA; f = 1 kHz	h_{ie}	typ.	2,7	3,6	4,5	7,5	kΩ	←
Reverse voltage transfer ratio								
V_{CE} = 5 V; I_C = 2 mA; f = 1 kHz	h_{re}	typ.	1,5	2	2	3	10^{-4}	
Small-signal current gain								
V_{CE} = 5 V; I_C = 2 mA; f = 1 kHz	h_{fe}	typ.	200	260	330	520		←
Output admittance								
V_{CE} = 5 V; I_C = 2 mA; f = 1 kHz	h_{oe}	typ.	18	24	30	50	μs	←
Base-emitter voltage								
V_{CE} = 5 V; I_C = 2 mA	V_{BE}		0,55 to 0,75				V	
		typ.	0,65				V	
V_{CE} = 5 V; I_C = 10 μA	V_{BE}	typ.	0,52				V	
V_{CE} = 1 V; I_C = 50 mA	V_{BE}	typ.	0,78				V	

Switching times

I_{Con} = 10 mA; I_{Bon} = $-I_{Boff}$ = 1 mA
V_{CC} = 10 V; R_L = 990 Ω

turn-on time ($t_d + t_r$)	t_{on}	typ.	85	ns
		<	150	ns
turn-off time ($t_s + t_f$)	t_{off}	typ.	480	ns
		<	800	ns

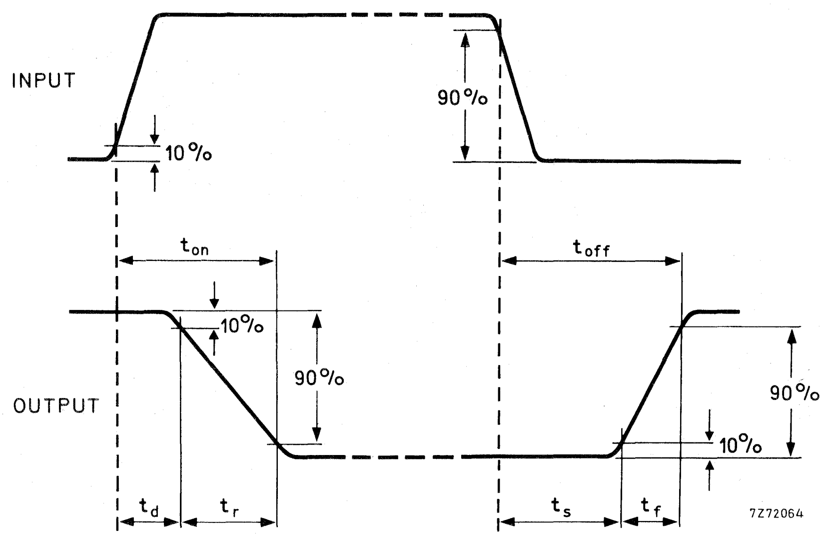


Fig. 2 Switching waveforms.

SILICON PLANAR EPITAXIAL TRANSISTORS

P-N-P silicon transistors, in a microminiature plastic envelope, intended for low level, low noise, low frequency purpose applications in hybrid circuits.

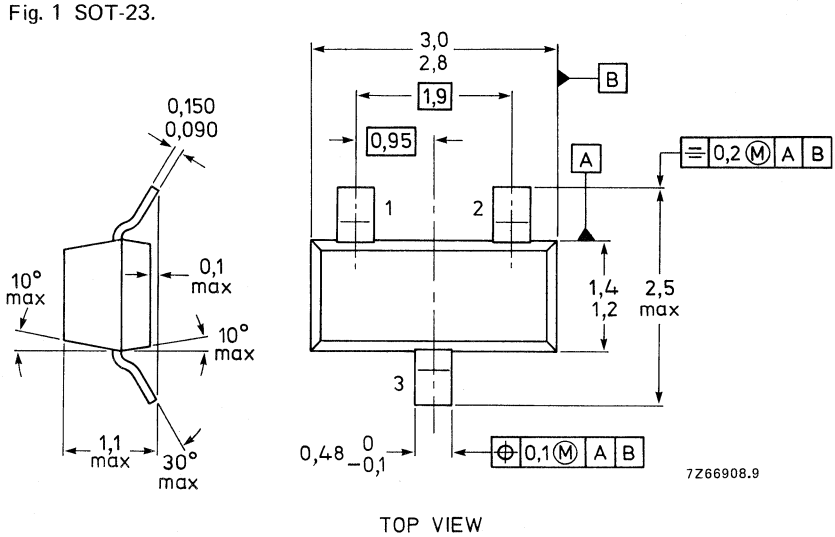
QUICK REFERENCE DATA

Collector-emitter voltage (V_{BE} = 0)	$-V_{CES}$	max.	32	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	32	V
Collector current (d.c.)	$-I_C$	max.	200	mA
Total power dissipation	P_{tot}	max.	150	mW
Junction temperature	T_j	max.	150	^oC
Transition frequency at f = 100 MHz $-V_{CE}$ = 5 V; $-I_C$ = 10 mA	f_T	typ.	180	MHz
Noise figure at f = 1 kHz $-V_{CE}$ = 5 V; $-I_C$ = 200 μA	F	typ.	2	dB

MECHANICAL DATA

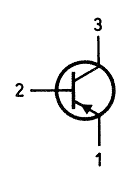
Dimensions in mm

Fig. 1 SOT-23.



Marking code

BCW61A = BA
BCW61B = BB
BCW61C = BC
BCW61D = BD



See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-emitter voltage (V_{BE} = 0)	$-V_{CES}$	max.	32	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	32	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5	V
Collector current (d.c.)	$-I_C$	max.	200	mA
Base current	$-I_B$	max.	50	mA
Total power dissipation up to T_{amb} = 100 °C**	P_{tot}	max.	150	mW
Storage temperature	T_{stg}	−55 to + 125		°C
Junction temperature	T_j	max.	150	°C

THERMAL CHARACTERISTICS*

$T_j = P x (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	50	K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280	K/W
From soldering points to ambient**	$R_{th\ s\text{-}a}$	=	90	K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Collector-emitter cut-off current				
V_{EB} = 0; $-V_{CE}$ = 32 V	$-I_{CES}$	<	20	nA
V_{EB} = 0; $-V_{CE}$ = 32 V; T_{amb} = 150 °C	$-I_{CES}$	<	20	μA
Emitter-base cut-off current				
I_C = 0; $-V_{EB}$ = 4 V	$-I_{EBO}$	<	20	nA
Saturation voltages				
$-I_C$ = 10 mA; $-I_B$ = 0,25 mA	$-V_{CEsat}$	0,06 to 0,25		V
	$-V_{BEsat}$	0,6 to 0,85		V
$-I_C$ = 50 mA; $-I_B$ = 1,25 mA	$-V_{CEsat}$	0,12 to 0,55		V
	$-V_{BEsat}$	0,68 to 1,05		V
Transition frequency at f = 100 MHz ▲				
$-V_{CE}$ = 5 V; $-I_C$ = 10 mA	f_T	typ.	180	MHz
Collector capacitance at f = 1 MHz				
→ $-V_{CB}$ = 10 V; $I_E = I_e$ = 0	C_c	typ.	4,5	pF
Emitter capacitance at f = 1 MHz				
$-V_{EB}$ = 0,5 V; $I_C = I_c$ = 0	C_e	typ.	11	pF
Noise figure at R_S = 2 kΩ				
$-V_{CE}$ = 5 V; $-I_C$ = 200 μA; B = 200 Hz	F	typ.	2	dB
		<	6	dB

* See *Thermal characteristics.*
** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.
▲ Measured under pulse conditions.

			A	B	C	D	
D.C. current gain							
$-V_{CE}$ = 5 V; $-I_C$ = 10 μA	h_{FE}	typ.	140	200	270	340	
		>	–	30	40	100	
		>	120	180	250	380	
$-V_{CE}$ = 5 V; $-I_C$ = 2 mA	h_{FE}	typ.	170	250	350	500	
		<	220	310	460	630	
$-V_{CE}$ = 1 V; $-I_C$ = 50 mA	h_{FE}	>	60	80	100	110	
Input impedance							
$-V_{CE}$ = 5 V; $-I_C$ = 2 mA; f = 1 kHz	h_{ie}	typ.	2,7	3,6	4,5	7,5	kΩ ←
Reverse voltage transfer ratio							
$-V_{CE}$ = 5 V; $-I_C$ = 2 mA; f = 1 kHz	h_{re}	typ.	1,5	2	2	3	10^{-4}
Small-signal current gain							
$-V_{CE}$ = 5 V; $-I_C$ = 2 mA; f = 1 kHz	h_{fe}	typ.	200	260	330	520	←
Output admittance							
$-V_{CE}$ = 5 V; $-I_C$ = 2 mA; f = 1 kHz	h_{oe}	typ.	18	24	30	50	μS ←
Base-emitter voltage							
$-V_{CE}$ = 5 V; $-I_C$ = 2 mA	V_{BE}		0,6 to 0,75				V
		typ.	0,65				V
$-V_{CE}$ = 5 V; $-I_C$ = 10 μA	V_{BE}	typ.	0,55				V
$-V_{CE}$ = 1 V; $-I_C$ = 50 mA	V_{BE}	typ.	0,72				V

Switching times

$-I_{Con}$ = 10 mA; $-I_{Bon}$ = I_{Boff} = 1 mA
$-V_{CC}$ = 10 V; R_L = 990 Ω

turn-on time ($t_d + t_r$)	t_{on}	typ.	85	ns
		<	150	ns
turn-off time ($t_s + t_f$)	t_{off}	typ.	480	ns
		<	800	ns

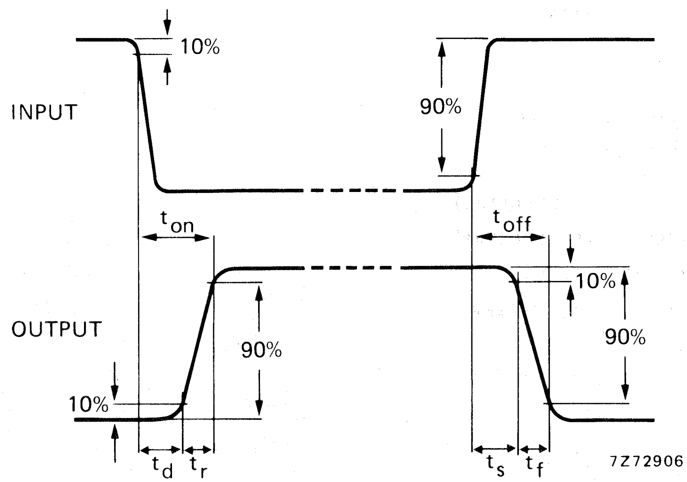


Fig. 2 Switching waveforms.

SILICON PLANAR EPITAXIAL TRANSISTORS

P-N-P transistors, in a microminiature plastic envelope, intended for low level general purpose applications in thick and thin-film circuits.

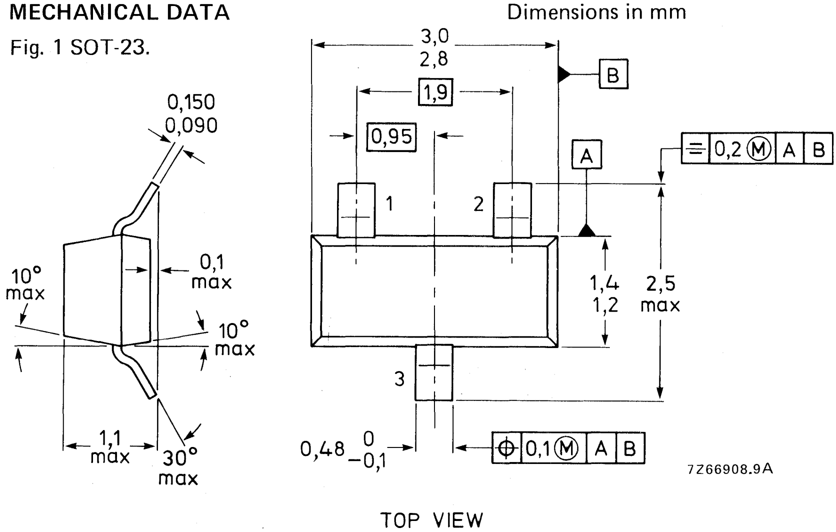
QUICK REFERENCE DATA

			BCW69	BCW70	
D.C. current gain at T_j = 25 °C $-I_C$ = 2 mA; $-V_{CE}$ = 5 V	h_{FE}	> <	120 260	215 500	
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	50		V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	45		V
Collector current (peak value)	$-I_{CM}$	max.	200		mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	350		mW
Junction temperature	T_j	max.	175		°C
Transition frequency at f = 35 MHz $-I_C$ = 10 mA; $-V_{CE}$ = 5 V	f_T	typ.	150		MHz
Noise figure at R_S = 2 kΩ $-I_C$ = 200 μA; $-V_{CE}$ = 5 V; f = 1 kHz; B = 200 Hz	F	<	10		dB

MECHANICAL DATA

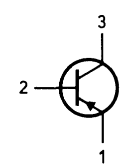
Fig. 1 SOT-23.

Dimensions in mm

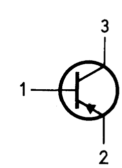


Marking code

BCW69 = H1
BCW70 = H2



BCW69R = H4
BCW70R = H5



R-types are available on request.

See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC134)

Collector-base voltage (open emitter) see Fig. 2	$-V_{CBO}$	max.	50	V
Collector-emitter voltage (V_{BE} = 0) see Fig. 2	$-V_{CES}$	max.	50	V
Collector-emitter voltage (open base) see Fig. 2 $-I_C$ = 2 mA	$-V_{CEO}$	max.	45	V
Emitter-base voltage (open collector) see Fig. 2	$-V_{EBO}$	max.	5	V
Collector current (d.c.)	$-I_C$	max.	100	mA
Collector current (peak value)	$-I_{CM}$	max.	200	mA
Total power dissipation up to T_{amb} = 25 °C**	P_{tot}	max.	350	mW
Storage temperature	T_{stg}		−65 to + 175	°C
Junction temperature	T_j	max.	175	°C

THERMAL CHARACTERISTICS*

$T_j = P \times (R_{th\,j\text{-}t} + R_{th\,t\text{-}s} + R_{th\,s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\,j\text{-}t}$	=	50	K/W
From tab to soldering points	$R_{th\,t\text{-}s}$	=	280	K/W
From soldering points to ambient**	$R_{th\,s\text{-}a}$	=	90	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current				
I_E = 0; $-V_{CB}$ = 20 V	$-I_{CBO}$	<	100	nA
I_E = 0; $-V_{CB}$ = 20 V; T_j = 100 °C	$-I_{CBO}$	<	10	μA
Base-emitter voltage				
$-I_C$ = 2 mA; $-V_{CE}$ = 5 V	$-V_{BE}$		600 to 750	mV
Saturation voltages	$-V_{CEsat}$	typ.	80	mV
		<	300	mV
$-I_C$ = 10 mA; $-I_B$ = 0,5 mA	$-V_{BEsat}$	typ.	720	mV
$-I_C$ = 50 mA; $-I_B$ = 2,5 mA	$-V_{CEsat}$	typ.	150	mV
	$-V_{BEsat}$	typ.	810	mV

* See *Thermal characteristics.*
** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

			BCW69	BCW70	
D.C. current gain					
$-I_C = 10\ \mu A$; $-V_{CE} = 5$ V	h_{FE}	typ.	90	150	
$-I_C = 2$ mA; $-V_{CE} = 5$ V	h_{FE}	>	120	215	
		<	260	500	
Collector capacitance at f = 1 MHz $I_E = I_e = 0$; $-V_{CB} = 10$ V	C_c	typ.	4,5		pF ←
Transition frequency at f = 35 MHz $-I_C = 10$ mA; $-V_{CE} = 5$ V	f_T	typ.	150		MHz
Noise figure at $R_S = 2\ k\Omega$ $-I_C = 200\ \mu A$; $-V_{CE} = 5$ V f = 1 kHz; B = 200 Hz	F	<	10		dB

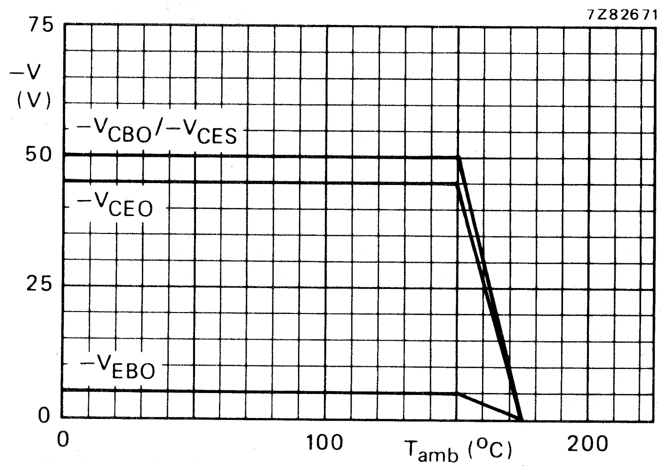


Fig. 2 Voltage derating curve.

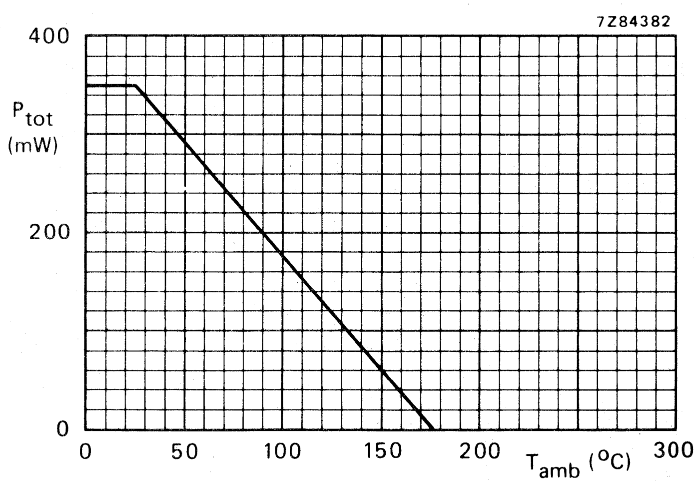


Fig. 3 Power derating curve.

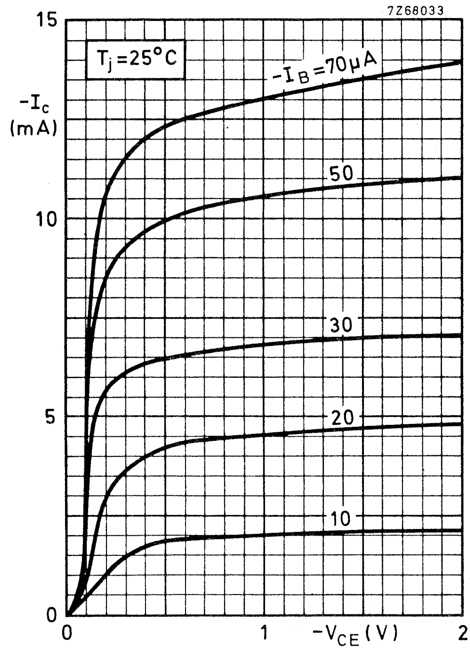


Fig. 4.

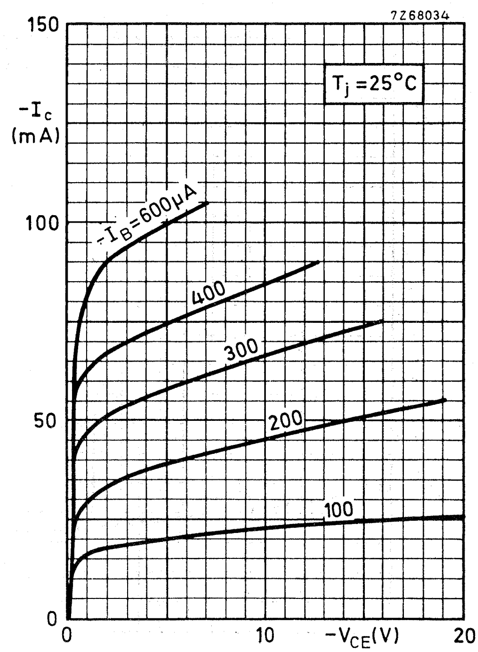


Fig. 5.

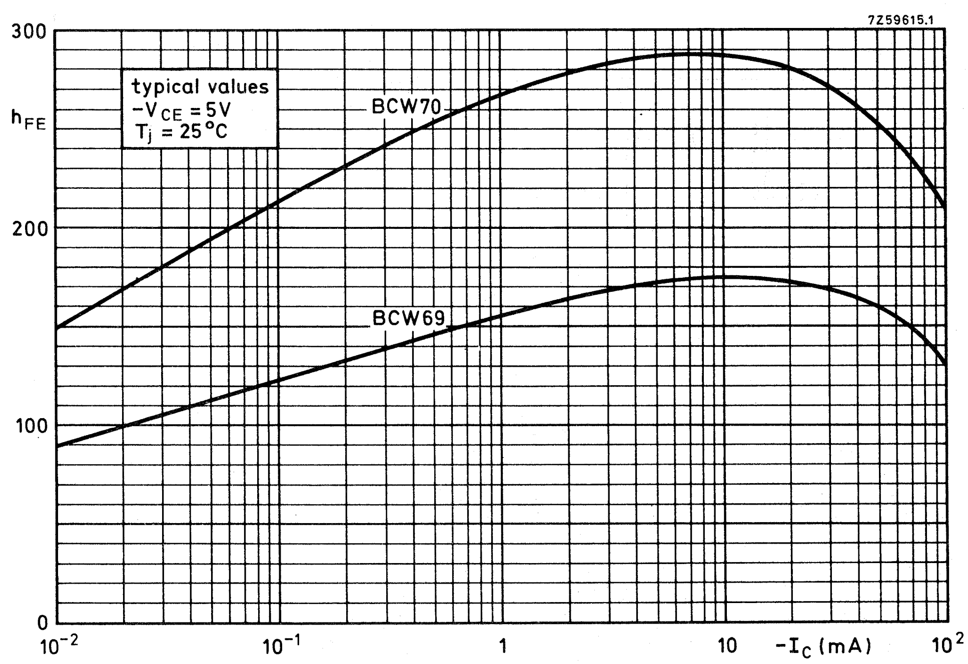


Fig. 6 D.C. current gain.

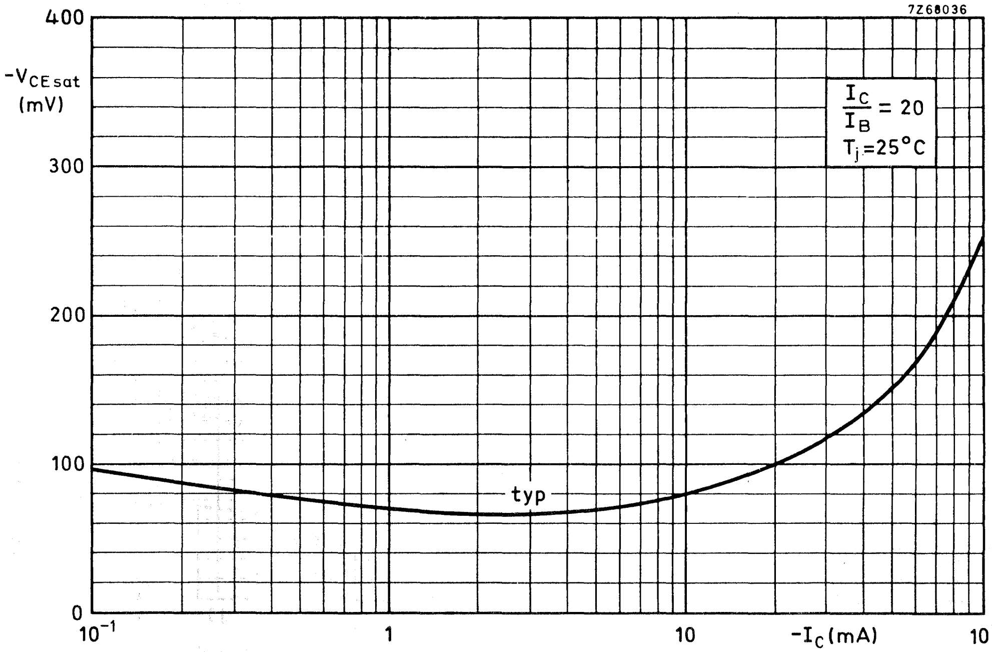

7Z68036
400
$-V_{CEsat}$
(mV)
300
200
100
0
$\frac{I_C}{I_B} = 20$
$T_j = 25°C$
typ
10^{-1}
1
10
$-I_C$ (mA)
10^2

Fig. 7.

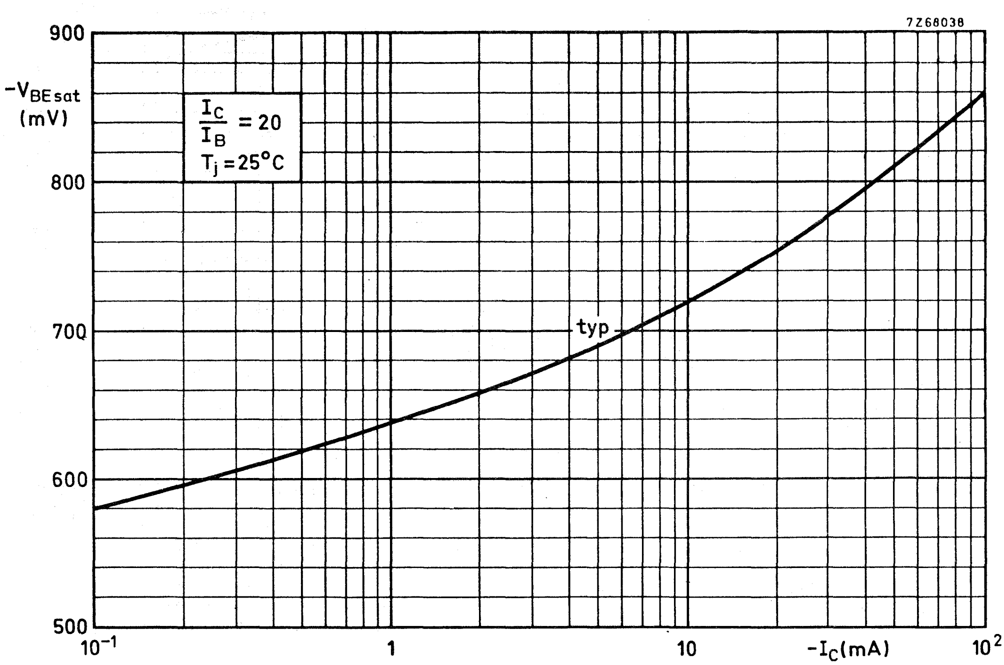

7Z68038
900
$-V_{BEsat}$
(mV)
800
700
600
500
$\frac{I_C}{I_B} = 20$
$T_j = 25°C$
typ
10^{-1}
1
10
$-I_C$ (mA)
10^2

Fig. 8.

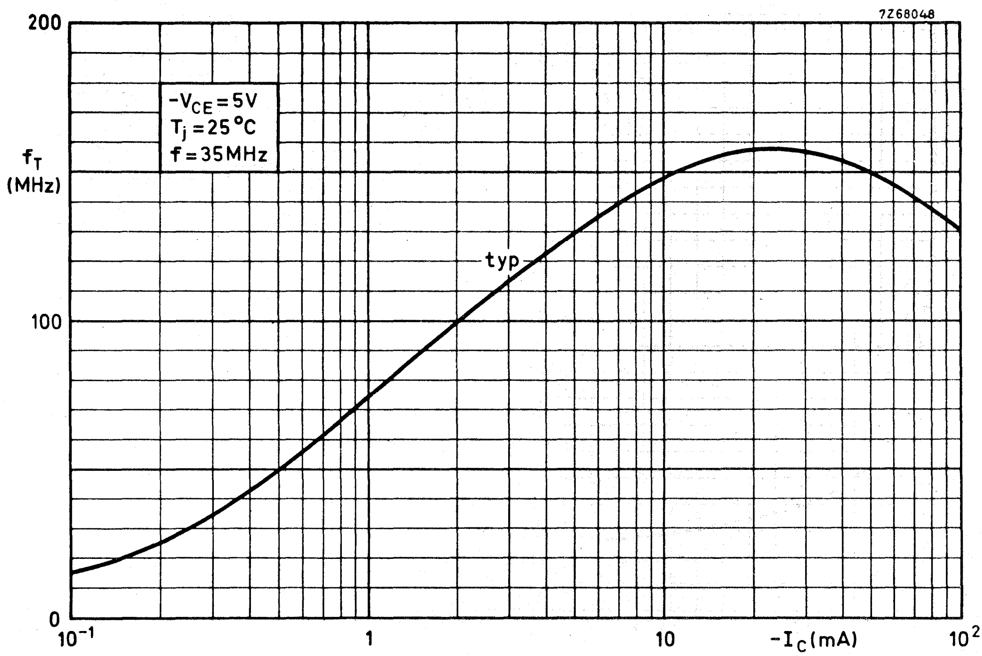


Fig. 9.

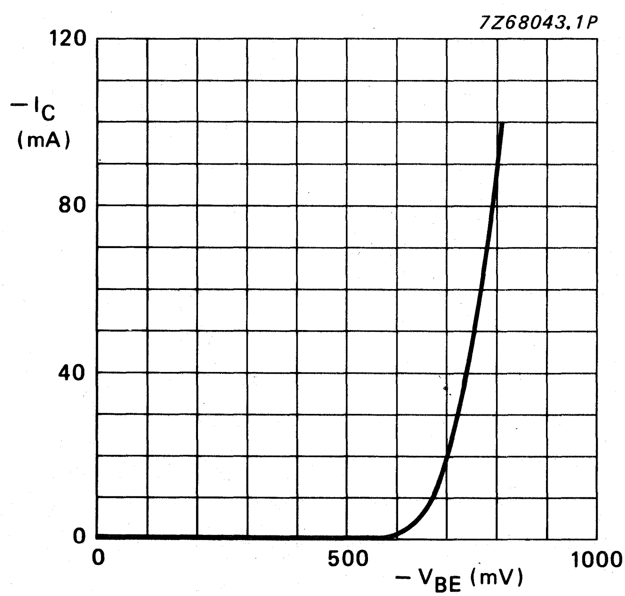


Fig. 10; $-V_{CE}$ = 5 V; T_j = 25 °C; typical values.

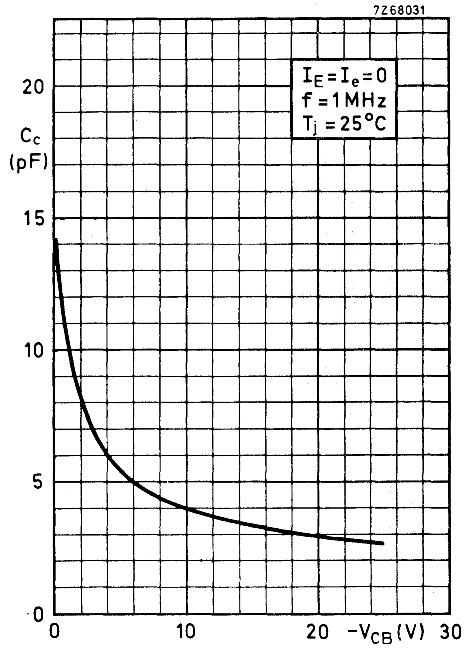

7Z68031
$I_E = I_e = 0$
f = 1 MHz
T_j = 25 °C
C_c (pF)
20
15
10
5
0
0
10
20
$-V_{CB}$ (V)
30

Fig. 11.

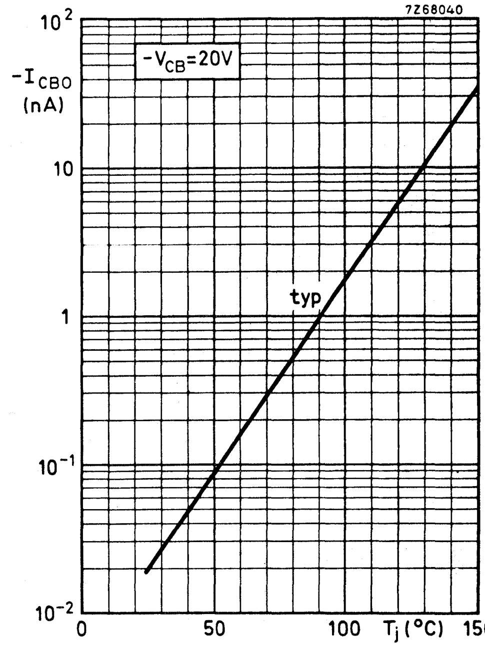

7Z68040
$-V_{CB}$=20V
$-I_{CBO}$ (nA)
10^2
10
1
10^{-1}
10^{-2}
typ
0
50
100
T_j (°C)
150

Fig. 12.

SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N transistors, in a microminiature plastic envelope, intended for low level general purpose applications in thick and thin-film circuits.

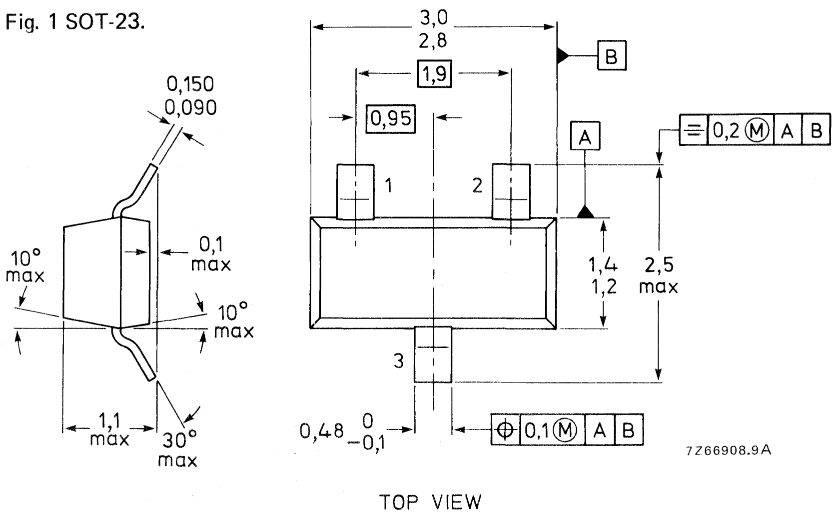
QUICK REFERENCE DATA

			BCW71	BCW72	
D.C. current gain at T_j = 25 °C; I_C = 2 mA; V_{CE} = 5 V	h_{FE}	>	110	200	
		<	220	450	
Collector-base voltage (open emitter)	V_{CBO}	max.	50		V
Collector-emitter voltage (open base)	V_{CEO}	max.	45		V
Collector current (peak value)	I_{CM}	max.	200		mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	350		mW
Junction temperature	T_j	max.	175		°C
Transition frequency at f = 35 MHz; I_C = 10 mA; V_{CE} = 5 V	f_T	typ.	300		MHz
Noise figure at R_S = 2 kΩ; I_C = 200 μA; V_{CE} = 5 V; f = 1 kHz; B = 200 Hz	F	<	10		dB

MECHANICAL DATA

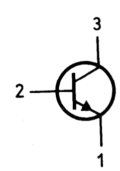
Dimensions in mm

Fig. 1 SOT-23.

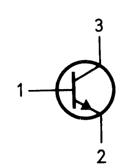


Marking code

BCW71 = K1
BCW72 = K2



BCW71R = K4
BCW72R = K5



R-types are available on request.

See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter) see Fig. 2	V_{CBO}	max.	50	V
Collector-emitter voltage (open base) see Fig. 2, I_C = 2 mA	V_{CEO}	max.	45	V
Emitter-base voltage (open collector) see Fig. 2	V_{EBO}	max.	5	V
Collector current (d.c.)	I_C	max.	100	mA
Collector current (peak value)	I_{CM}	max.	200	mA
Total power dissipation up to T_{amb} = 25 °C**	P_{tot}	max.	350	mW
Storage temperature	T_{stg}		−65 to +175	°C
Junction temperature	T_j	max.	175	°C

THERMAL CHARACTERISTICS*

$$T_j = Px\,(R_{th\,j\text{-}t} + R_{th\,t\text{-}s} + R_{th\,s\text{-}a}) + T_{amb}$$

Thermal resistance

From junction to tab	$R_{th\,j\text{-}t}$	=	50	K/W
From tab to soldering points	$R_{th\,t\text{-}s}$	=	280	K/W
From soldering points to ambient**	$R_{th\,s\text{-}a}$	=	90	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current				
I_E = 0; V_{CB} = 20 V	I_{CBO}	<	100	nA
I_E = 0; V_{CB} = 20 V; T_j = 100 °C	I_{CBO}	<	10	μA
Base emitter voltage				
I_C = 2 mA; V_{CE} = 5 V	V_{BE}		550 to 700	mV
Saturation voltages				
I_C = 10 mA; I_B = 0,5 mA	V_{CEsat}	typ.	120	mV
		<	250	mV
	V_{BEsat}	typ.	750	mV
I_C = 50 mA; I_B = 2,5 mA	V_{CEsat}	typ.	210	mV
	V_{BEsat}	typ.	850	mV

* See *Thermal characteristics.*
** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

			BCW71	BCW72	
D.C. current gain					
I_C = 10 μA; V_{CE} = 5 V	h_{FE}	typ.	90	150	
I_C = 2 mA; V_{CE} = 5 V	h_{FE}	>	110	200	
		<	220	450	
Collector capacitance at f = 1 MHz $I_E = I_e = 0$; V_{CB} = 10 V	C_c	typ.	2,5		pF ←
Transition frequency at f = 35 MHz I_C = 10 mA; V_{CE} = 5 V	f_T	typ.	300		MHz
Noise figure at R_S = 2 kΩ I_C = 200 μA; V_{CE} = 5 V f = 1 kHz; B = 200 Hz	F	<	10		dB

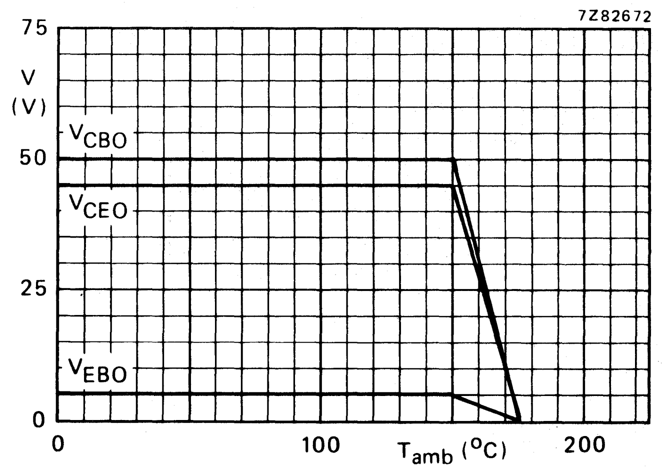


Fig. 2 Voltage derating curves.

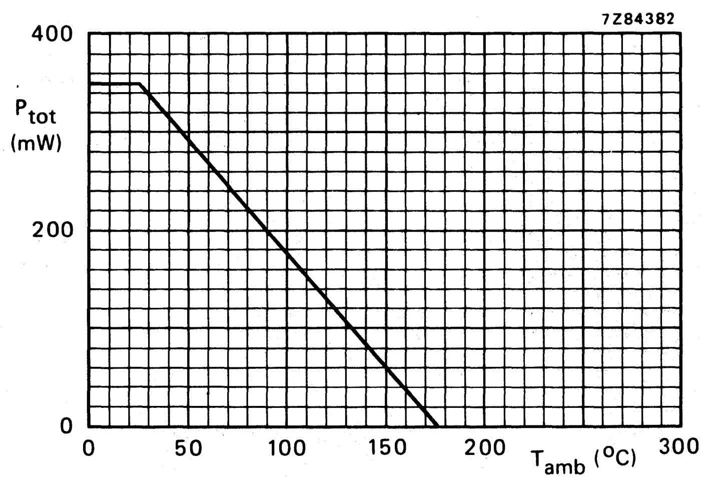


Fig. 3 Power derating curve.

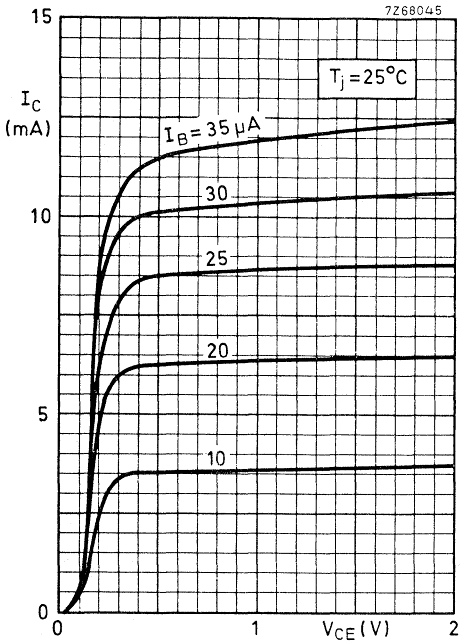


Fig. 4.

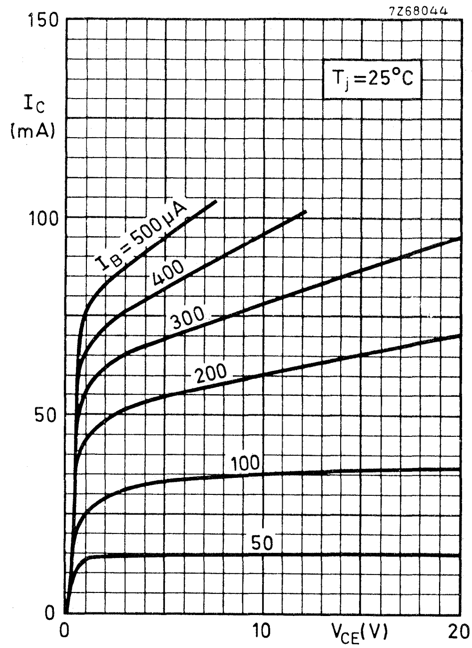


Fig.5.

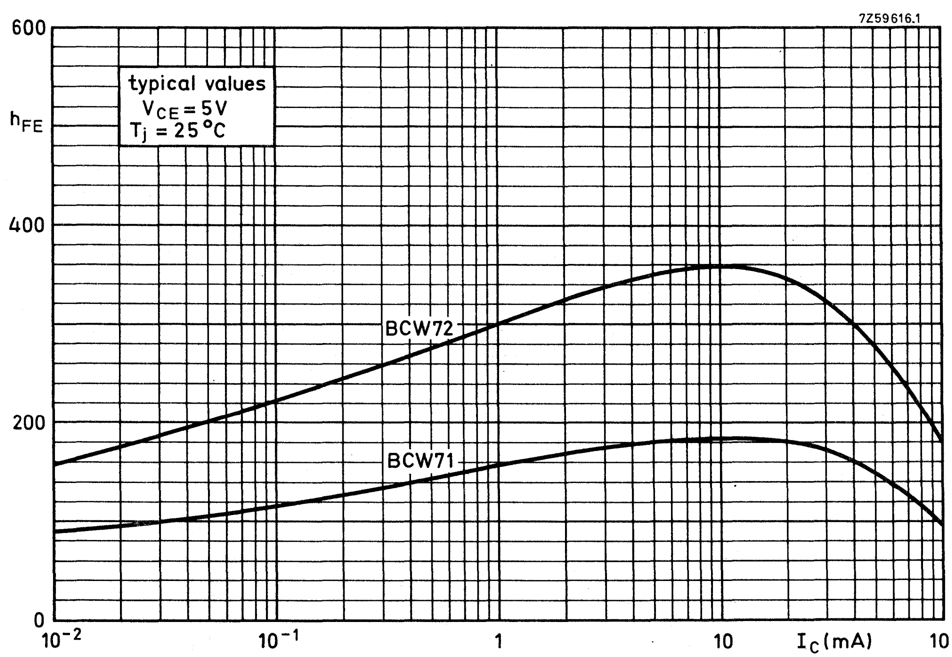


Fig. 6 D.C. current gain.

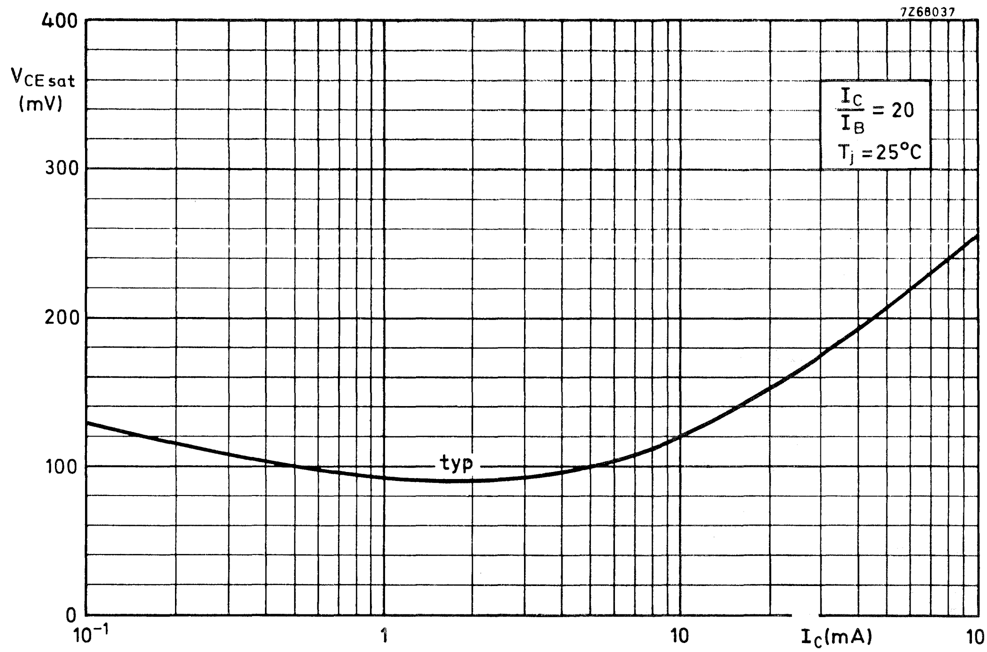

7Z68037
400
300
200
100
0
V_{CEsat} (mV)
$\frac{I_C}{I_B} = 20$
$T_j = 25°C$
typ
10^{-1}
1
10
I_C(mA)
10^2

Fig. 7.

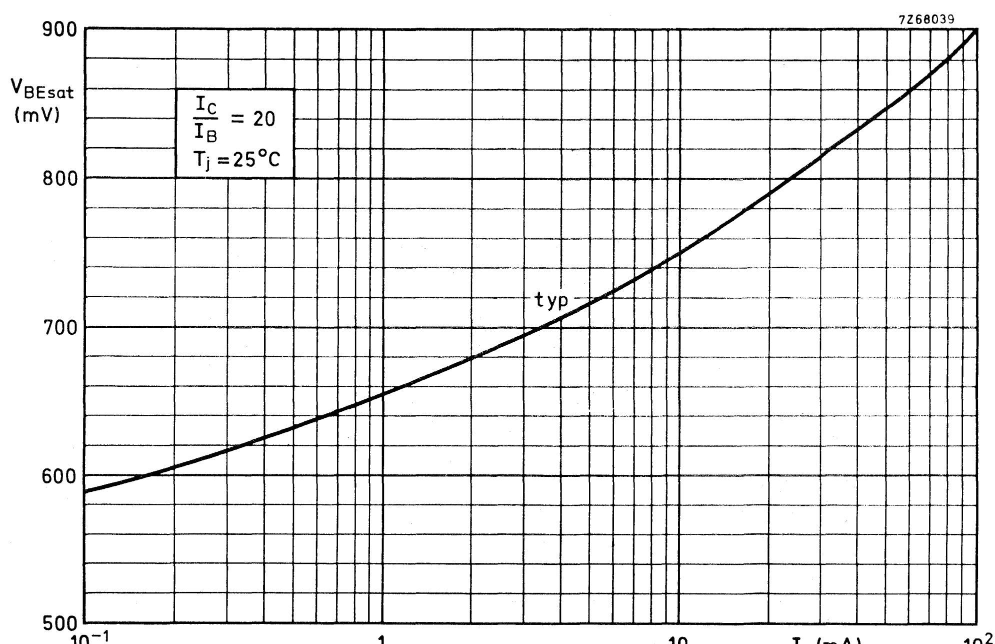

7Z68039
900
800
700
600
500
V_{BEsat} (mV)
$\frac{I_C}{I_B} = 20$
$T_j = 25°C$
typ
10^{-1}
1
10
I_C(mA)
10^2

Fig. 8.

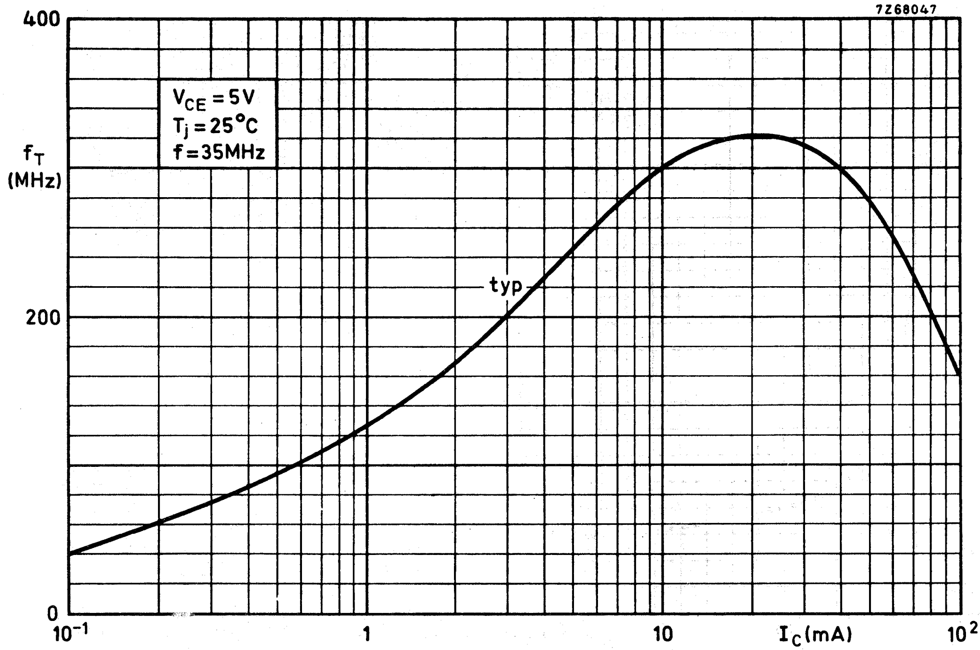


Fig. 9.

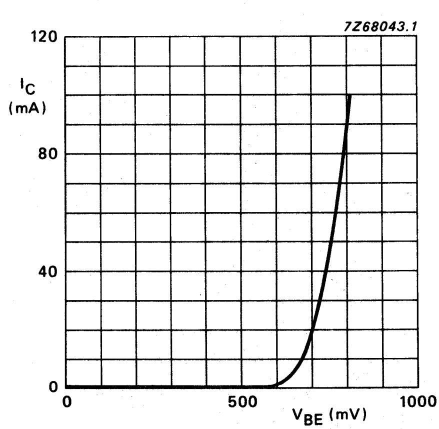


Fig. 10 $V_{CE} = 5$ V; $T_j = 25$ °C; typical values.

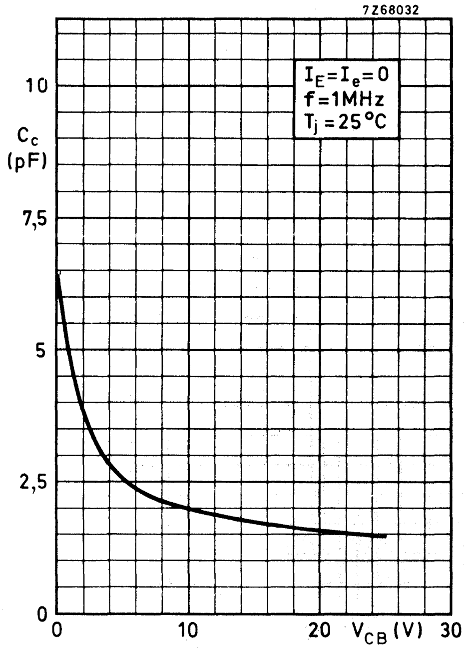

7Z68032
$I_E = I_e = 0$
f = 1MHz
$T_j = 25\,°C$
C_c
(pF)
10
7,5
5
2,5
0
0
10
20
V_{CB} (V)
30

Fig. 11.

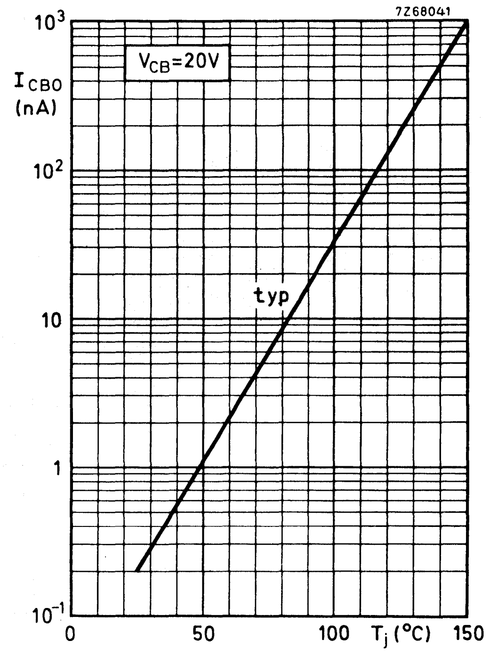

7Z68041
$V_{CB} = 20V$
I_{CBO}
(nA)
10^3
10^2
10
1
10^{-1}
typ
0
50
100
T_j (°C)
150

Fig. 12.

SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N transistors, in a microminiature plastic envelope, intended for low level general purpose applications in thick and thin-film circuits.

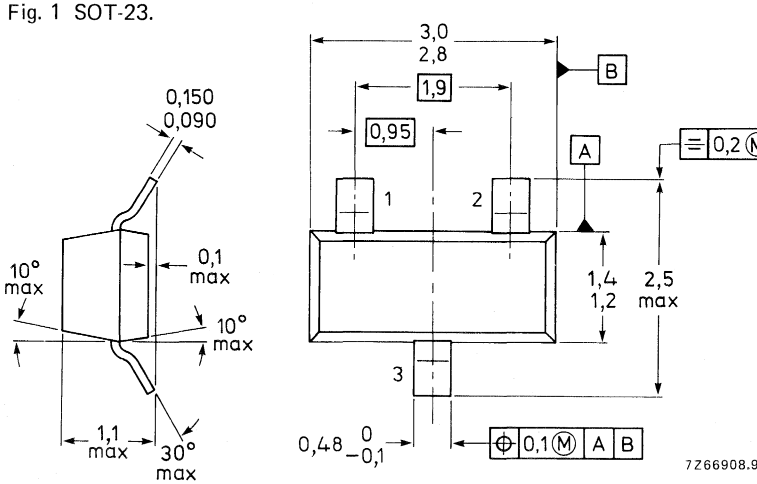
QUICK REFERENCE DATA

Collector-base voltage (open emitter)	V_{CBO}	max.	50	V
Collector-emitter voltage (open base)	V_{CEO}	max.	45	V
Collector current (peak value)	I_{CM}	max.	200	mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	350	mW
Junction temperature	T_j	max.	175	°C
D.C. current gain at T_j = 25 °C I_C = 2 mA; V_{CE} = 5 V	h_{FE}	$>$ $<$	420 800	
Transition frequency at f = 35 MHz I_C = 10 mA; V_{CE} = 5 V	f_T	typ.	300	MHz
Noise figure at R_S = 2 kΩ I_C = 200 μA; V_{CE} = 5 V; f = 1 kHz; B = 200 Hz	F	$<$	10	dB

MECHANICAL DATA

Dimensions in mm

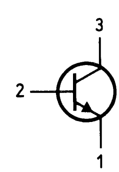
Fig. 1 SOT-23.



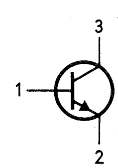
TOP VIEW

Marking code

BCW81 = K3



BCW81R = K31



R-types are available on request

See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter) see Fig. 2	V_{CBO}	max.	50 V
Collector-emitter voltage (open base) see Fig. 2 I_C = 2 mA	V_{CEO}	max.	45 V
Emitter-base voltage (open collector) see Fig. 2	V_{EBO}	max.	5 V
Collector current (d.c.)	I_C	max.	100 mA
Collector current (peak value)	I_{CM}	max.	200 mA
Total power dissipation up to T_{amb} = 25 °C**	P_{tot}	max.	350 mW
Storage temperature	T_{stg}	−65 to + 175	°C
Junction temperature	T_j	max.	175 °C

THERMAL CHARACTERISTICS*

$$T_j = P \times (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	50 K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280 K/W
From soldering points to ambient**	$R_{th\ s\text{-}a}$	=	90 K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current			
I_E = 0; V_{CB} = 20 V	I_{CBO}	<	100 nA
I_E = 0; V_{CB} = 20 V; T_j = 100 °C	I_{CBO}	<	10 μA
Base emitter voltage			
I_C = 2 mA; V_{CE} = 5 V	V_{BE}	550 to 700	mV
Saturation voltages			
I_C = 10 mA; I_B = 0,5 mA	V_{CEsat}	typ.	120 mV
		<	250 mV
	V_{BEsat}	typ.	750 mV
I_C = 50 mA; I_B = 2,5 mA	V_{CEsat}	typ.	210 mV
	V_{BEsat}	typ.	850 mV

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm

D.C. current gain $I_C = 2$ mA; $V_{CE} = 5$ V	h_{FE}	> <	420 800
Collector capacitance at f = 1 MHz $I_E = I_e = 0$; $V_{CB} = 10$ V	C_c	typ.	2,5 pF ←
Transition frequency at f = 35 MHz $I_C = 10$ mA; $V_{CE} = 5$ V	f_T	typ.	300 MHz
Noise figure at $R_S = 2$ kΩ $I_C = 200$ μA; $V_{CE} = 5$ V f = 1 kHz; B = 200 Hz	F	<	10 dB

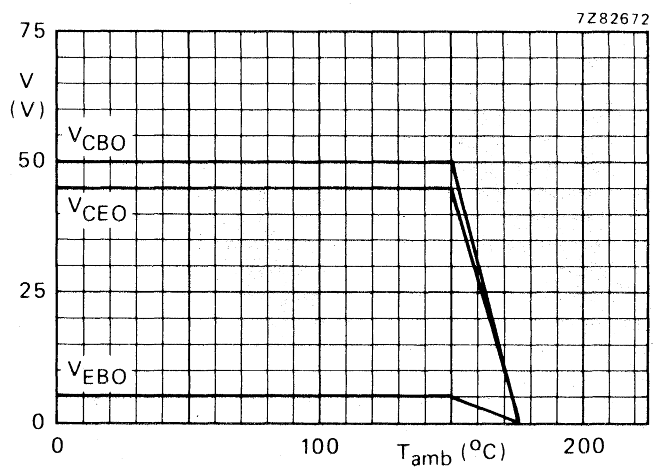


Fig. 2 Voltage derating curves.

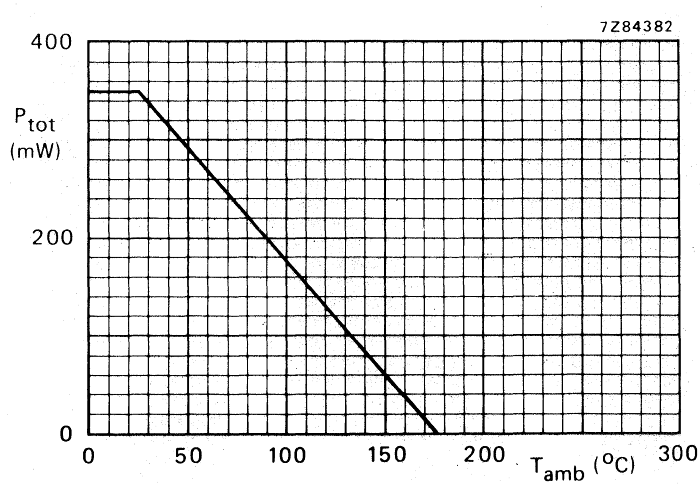


Fig. 3 Power derating curve.

SILICON PLANAR EPITAXIAL TRANSISTORS

P-N-P transistors, in a microminiature plastic envelope, intended for low level general purpose applications in thick and thin-film circuits.

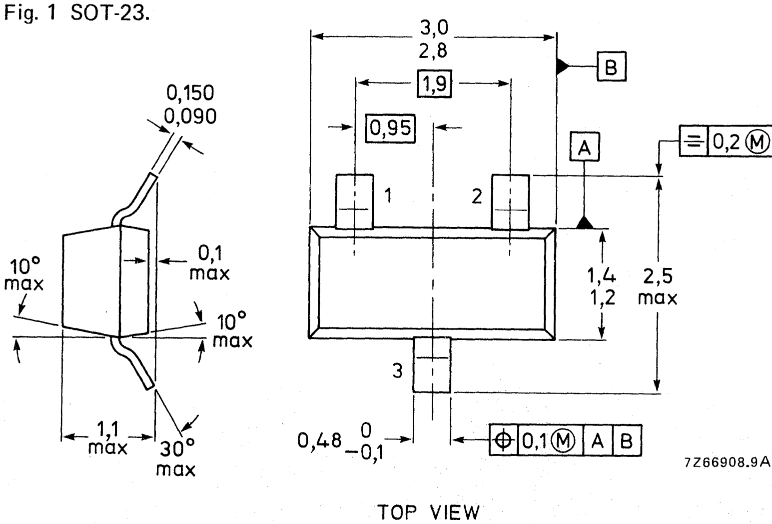
QUICK REFERENCE DATA

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	80	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	60	V
Collector current (peak value)	$-I_{CM}$	max.	200	mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	350	mW
Junction temperature	T_j	max.	175	°C
D.C. current gain at T_j = 25 °C $-I_C$ = 2 mA; $-V_{CE}$ = 5 V	h_{FE}	> <	120 260	
Transition frequency at f = 35 MHz $-I_C$ = 10 mA; $-V_{CE}$ = 5 V	f_T	typ.	150	MHz
Noise figure at R_S = 2 kΩ $-I_C$ = 200 μA; $-V_{CE}$ = 5 V; f = 1 kHz; B = 200 Hz	F	<	10	dB

MECHANICAL DATA

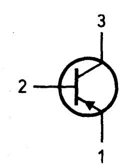
Dimensions in mm

Fig. 1 SOT-23.

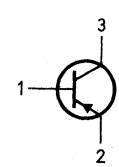


Marking code

BCW89 = H3



BCW89R = H31



R-types are available on request.

See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter) see Fig. 2	$-V_{CBO}$	max.	80	V
Collector-emitter voltage (V_{BE} = 0) see Fig. 2	$-V_{CES}$	max.	60	V
Collector-emitter voltage (open base) see Fig. 2 $-I_C$ = 2 mA	$-V_{CEO}$	max.	60	V
Emitter-base voltage (open collector) see Fig. 2	$-V_{EBO}$	max.	5	V
Collector current (d.c.)	$-I_C$	max.	100	mA
Collector current (peak value)	$-I_{CM}$	max.	200	mA
Total power dissipation up to T_{amb} = 25 °C**	P_{tot}	max.	350	mW
Storage temperature	T_{stg}		−65 to + 175	°C
Junction temperature	T_j	max.	175	°C

THERMAL CHARACTERISTICS*

$T_j = P \times (R_{th\,j\text{-}t} + R_{th\,t\text{-}s} + R_{th\,s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\,j\text{-}t}$	=	50	K/W
From tab to soldering points	$R_{th\,t\text{-}s}$	=	280	K/W
From soldering points to ambient**	$R_{th\,s\text{-}a}$	=	90	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current				
I_E = 0; $-V_{CB}$ = 20 V	$-I_{CBO}$	<	100	nA
I_E = 0; $-V_{CB}$ = 20 V; T_j = 100 °C	$-I_{CBO}$	<	10	μA
Base-emitter voltage				
$-I_C$ = 2 mA; $-V_{CE}$ = 5 V; T_j = 25 °C	$-V_{BE}$		600 to 750	mV
Saturation voltages				
$-I_C$ = 10 mA; $-I_B$ = 0,5 mA	$-V_{CEsat}$	typ.	80	mV
		<	300	mV
	$-V_{BEsat}$	typ.	720	mV
$-I_C$ = 50 mA; $-I_B$ = 2,5 mA	$-V_{CEsat}$	typ.	150	mV
	$-V_{BEsat}$	typ.	810	mV

* See *Thermal characteristics.*
** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

D.C. current gain			
$-I_C = 10\ \mu A$; $-V_{CE} = 5$ V	h_{FE}	typ.	90
$-I_C = 2$ mA; $-V_{CE} = 5$ V	h_{FE}	> <	120 260
Collector capacitance at f = 1 MHz			
$I_E = I_e = 0$; $-V_{CB} = 10$ V	C_c	typ.	4,5 pF ←
Transition frequency at f = 35 MHz			
$-I_C = 10$ mA; $-V_{CE} = 5$ V	f_T	typ.	150 MHz
Noise figure at $R_S = 2\ k\Omega$			
$-I_C = 200\ \mu A$; $-V_{CE} = 5$ V f = 1 kHz; B = 200 Hz	F	<	10 dB

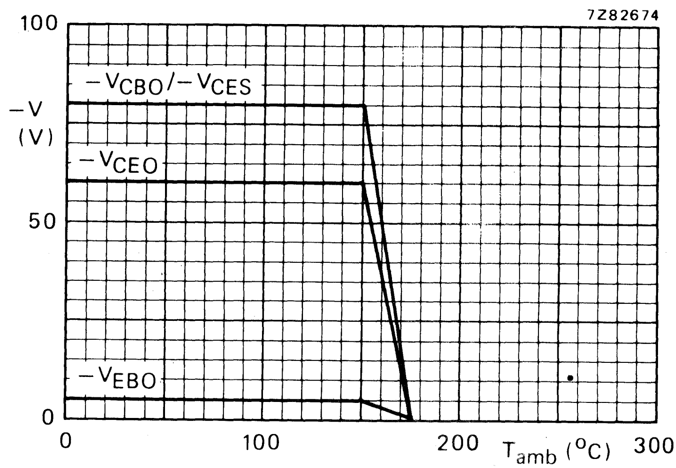


Fig. 2 Voltage derating curves.

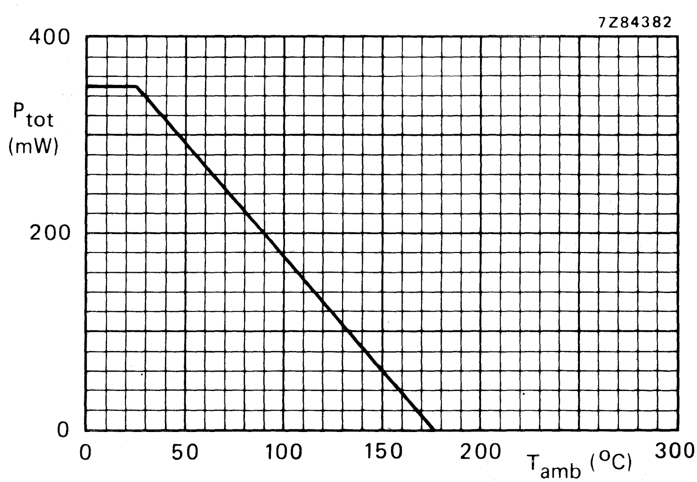


Fig. 3 Power derating curve.

SILICON PLANAR EPITAXIAL TRANSISTORS

P-N-P transistors, in a SOT-23 plastic envelope, intended for application in thick and thin-film circuits. These transistors are intended for general purposes as well as saturated switching and driver applications for industrial service.
N-P-N complements are BCX19 and BCX20 respectively.

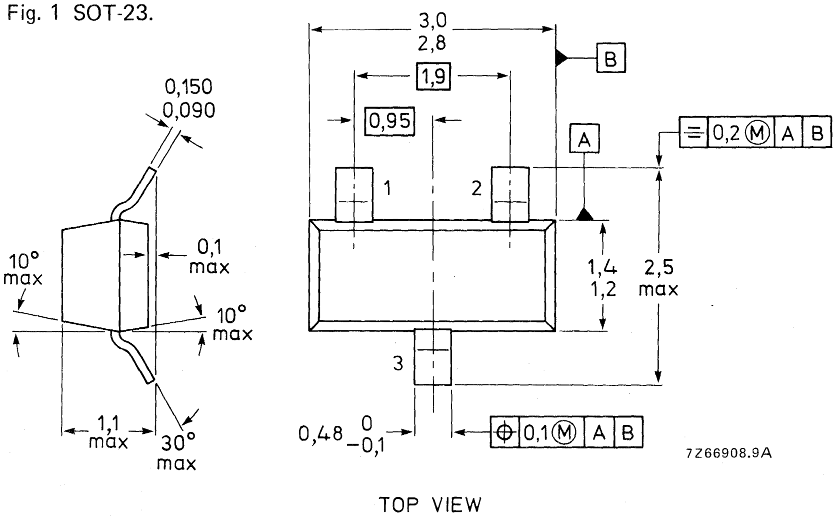
QUICK REFERENCE DATA

			BCX17	BCX18	
Collector-emitter voltage (V_{BE} = 0)	$-V_{CES}$	max.	50	30	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	45	25	V
Collector current (peak value)	$-I_{CM}$	max.	1000		mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	425		mW
Junction temperature	T_j	max.	175		°C
D.C. current gain $-I_C$ = 100 mA; $-V_{CE}$ = 1 V	h_{FE}		100 to 600		
Transition frequency $-I_C$ = 10 mA; $-V_{CE}$ = 5 V; f = 35 MHz	f_T	typ.	100		MHz

MECHANICAL DATA

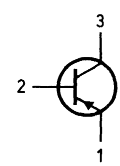
Dimensions in mm

Fig. 1 SOT-23.

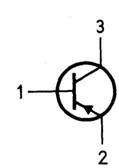


Marking code

BCX17 = T1
BCX18 = T2



BCX17R = T4
BCX18R = T5



R-types are available on request

See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BCX17	BCX18	
Collector-emitter voltage (V_{BE} = 0) (see Fig. 2)	$-V_{CES}$	max.	50	30	V
Collector-emitter voltage (open base) $-I_C$ = 10 mA (see Fig. 2)	$-V_{CEO}$	max.	45	25	V
Emitter-base voltage (open collector) (see Fig. 2)	$-V_{EBO}$	max.	5	5	V
Collector current (d.c.)	$-I_C$	max.	500		mA
Collector current (peak value)	$-I_{CM}$	max.	1000		mA
Emitter current (peak value)	I_{EM}	max.	1000		mA
Base current (d.c.)	$-I_B$	max.	100		mA
Base current (peak value)	$-I_{BM}$	max.	200		mA
Total power dissipation up to T_{amb} = 25 °C*	P_{tot}	max.	425		mW
Storage temperature	T_{stg}		–65 to + 175		°C
Junction temperature	T_j	max.	175		°C

THERMAL CHARACTERISTICS**

$T_j = P\,(R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	30	K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	260	K/W
From soldering points to ambient*	$R_{th\ s\text{-}a}$	=	60	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current				
$I_E = 0$; $-V_{CB}$ = 20 V	$-I_{CBO}$	<	100	nA
$I_E = 0$; $-V_{CB}$ = 20 V; T_j = 150 °C	$-I_{CBO}$	<	5	μA
Emitter cut-off current				
$I_C = 0$; $-V_{EB}$ = 5 V	$-I_{EBO}$	<	10	μA
Base-emitter voltage ▲				
$-I_C$ = 500 mA; $-V_{CE}$ = 1 V	$-V_{BE}$	<	1,2	V
Saturation voltage				
$-I_C$ = 500 mA; $-I_B$ = 50 mA	$-V_{CEsat}$	<	620	mV

* Mounted on a ceramic substrate of 15 mm x 15 mm x 0,7 mm.
** See *Thermal characteristics.*
▲ $-V_{BE}$ decreases by about 2 mV/°C with increasing temperature.

D.C. current gain

$-I_C = 100$ mA; $-V_{CE} = 1$ V	h_{FE}	100 to 600
$-I_C = 300$ mA; $-V_{CE} = 1$ V	h_{FE}	> 70
$-I_C = 500$ mA; $-V_{CE} = 1$ V	h_{FE}	> 40
Transition frequency at f = 35 MHz		
$-I_C = 10$ mA; $-V_{CE} = 5$ V	f_T	typ. 100 MHz
Collector capacitance at f = 1 MHz		
$I_E = I_e = 0$; $-V_{CB} = 10$ V	C_c	typ. 8 pF

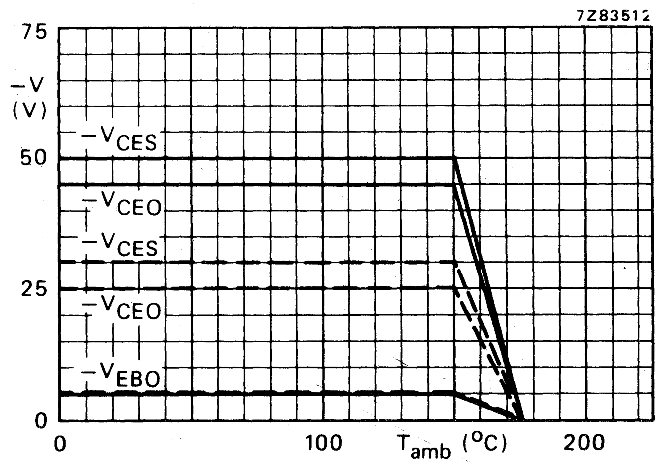


Fig. 2 Voltage derating curves. — — — BCX18 ——— BCX17.

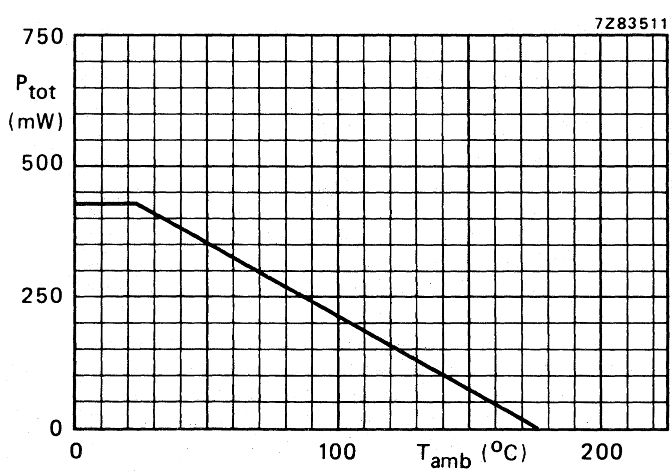


Fig. 3 Power derating curve.

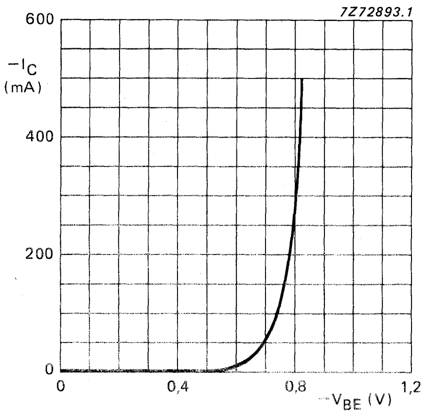


Fig. 4 $-V_{CE} = 1$ V; $T_j = 25\ ^oC$; typical values.

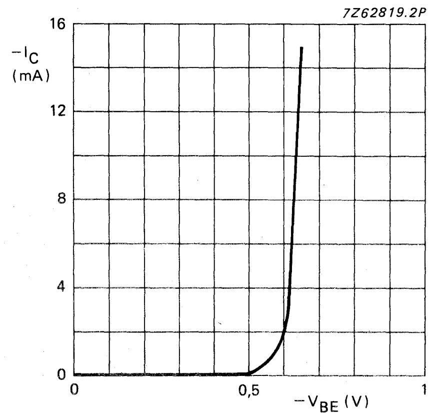


Fig. 5 $V_{CE} = 5$ V; $T_j = 25\ ^oC$; typical values.

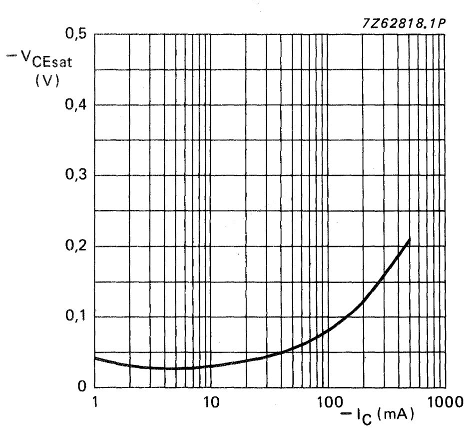


Fig. 6 $I_C/I_B = 10$; $T_j = 25\ ^oC$; typical values.

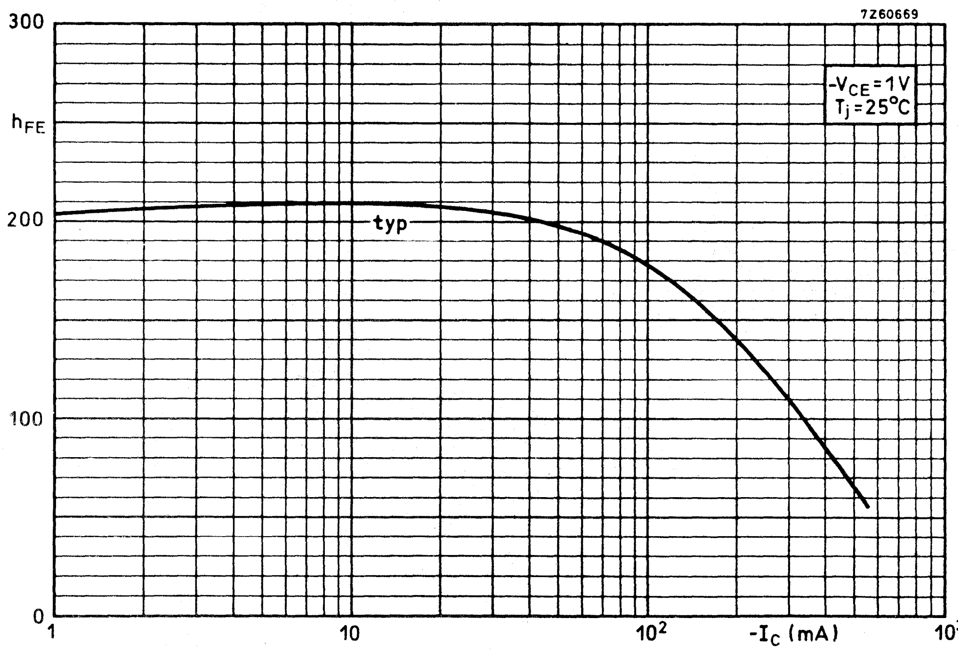

7Z60669
300
h_{FE}
200
100
0
1
10
10^2
$-I_C$ (mA)
10^3
$-V_{CE} = 1$ V
$T_j = 25°C$
typ

Fig. 7.

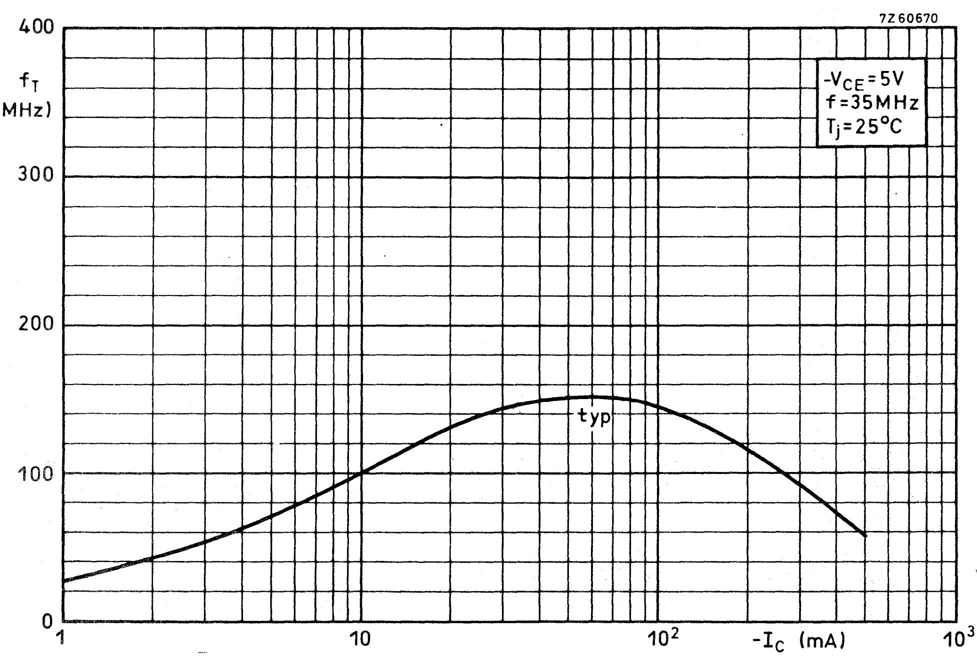

7Z60670
400
f_T
(MHz)
300
200
100
0
1
10
10^2
$-I_C$ (mA)
10^3
$-V_{CE} = 5$ V
f = 35 MHz
$T_j = 25°C$
typ

Fig. 8.

SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N transistors, in a SOT-23 plastic envelope, intended for application in thick and thin-film circuits. These transistors are intended for general purposes as well as saturated switching and driver applications for industrial service.
P-N-P complements are BCX17 and BCX18 respectively.

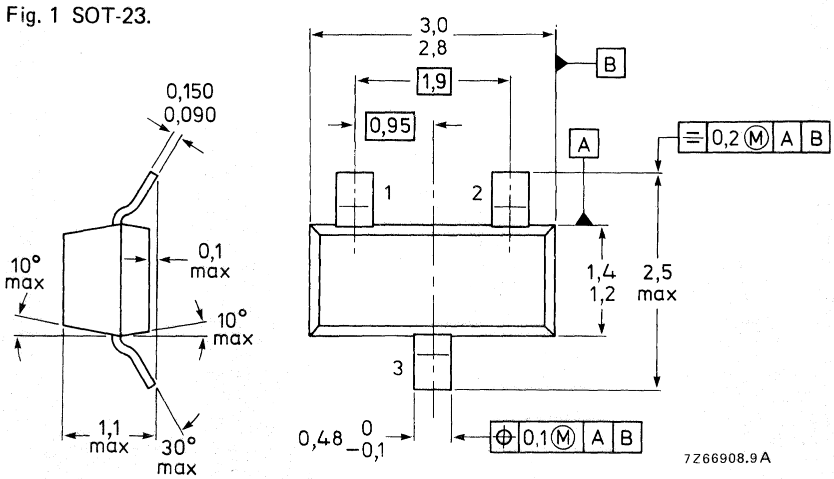
QUICK REFERENCE DATA

			BCX19	BCX20	
Collector-emitter voltage (V_{BE} = 0)	V_{CES}	max.	50	30	V
Collector-emitter voltage (open base)	V_{CEO}	max.	45	25	V
Collector current (peak value)	I_{CM}	max.	1000		mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	425		mW
Junction temperature	T_j	max.	175		°C
D.C. current gain I_C = 100 mA; V_{CE} = 1 V	h_{FE}		100 to 600		
Transition frequency I_C = 10 mA; V_{CE} = 5 V; f = 35 MHz	f_T	typ.	200		MHz

MECHANICAL DATA

Dimensions in mm

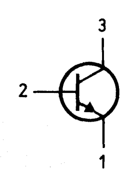
Fig. 1 SOT-23.



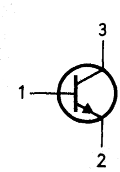
TOP VIEW

Marking code

BCX19 = U1
BCX20 = U2



BCX19R = U4
BCX20R = U5



R-types are available on request.

See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BCX19	BCX20	
Collector-emitter voltage (V_{BE} = 0) (see Fig. 2)	V_{CES}	max.	50	30	V
Collector-emitter voltage (open base) I_C = 10 mA (see Fig. 2)	V_{CEO}	max.	45	25	V
Emitter-base voltage (open collector) (see Fig. 2)	V_{EBO}	max.	5	5	V
Collector current (d.c.)	I_C	max.	500		mA
Collector current (peak value)	I_{CM}	max.	1000		mA
Emitter current (peak value)	$-I_{EM}$	max.	1000		mA
Base current (d.c.)	I_B	max.	100		mA
Base current (peak value)	I_{BM}	max.	200		mA
Total power dissipation up to T_{amb} = 25 °C*	P_{tot}	max.	425		mW
Storage temperature	T_{stg}		–65 to + 175		°C
Junction temperature	T_j	max.	175		°C

THERMAL CHARACTERISTICS**

$T_j = P\,(R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	30	K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	260	K/W
From soldering points to ambient*	$R_{th\ s\text{-}a}$	=	60	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current				
I_E = 0; V_{CB} = 20 V	I_{CBO}	<	100	nA
I_E = 0; V_{CB} = 20 V; T_j = 150 °C	I_{CBO}	<	5	μA
Emitter cut-off current				
I_C = 0; V_{EB} = 5 V	I_{EBO}	<	10	μA
Base emitter voltage ▲				
I_C = 500 mA; V_{CE} = 1 V	V_{BE}	<	1,2	V
Saturation voltage				
I_C = 500 mA; I_B = 50 mA	V_{CEsat}	<	620	mV

* Mounted on a ceramic substrate of 15 mm x 15 mm x 0,7 mm.
** See *Thermal characteristics.*
▲ V_{BE} decreases by about 2 mV/°C with increasing temperature.

D.C. current gain		
I_C = 100 mA; V_{CE} = 1 V	h_{FE}	100 to 600
I_C = 300 mA; V_{CE} = 1 V	h_{FE}	> 70
I_C = 500 mA; V_{CE} = 1 V	h_{FE}	> 40
Transition frequency at f = 35 MHz		
I_C = 10 mA; V_{CE} = 5 V	f_T	typ. 200 MHz
Collector capacitance at f = 1 MHz		
$I_E = I_e = 0$; V_{CB} = 10 V	C_c	typ. 5 pF

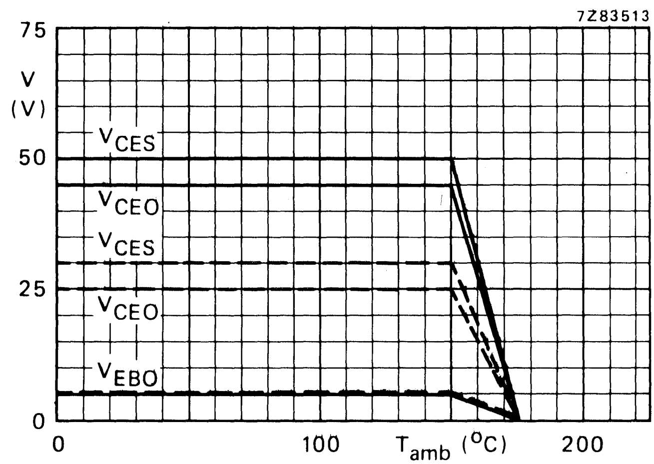


Fig. 2 Voltage derating curves. – – – BCX19/BCX20 ——.

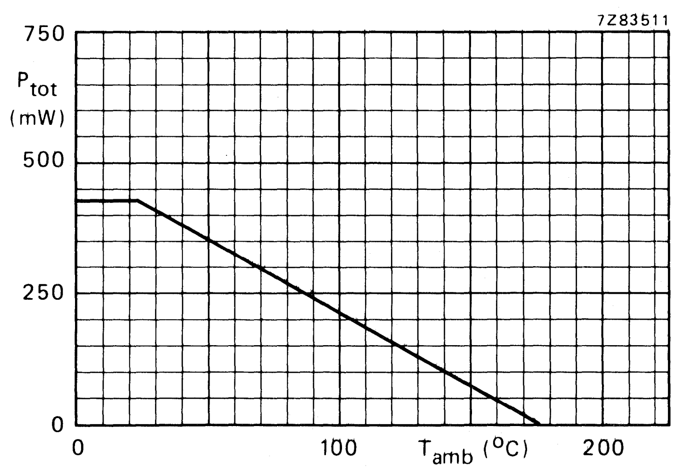


Fig. 3 Power derating curve.

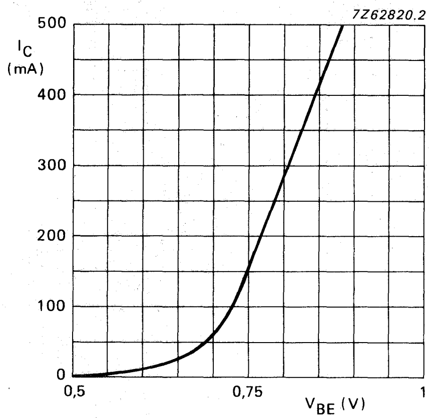


Fig. 4 V_{CE} 1 V; T_j =25 °C; typical values.

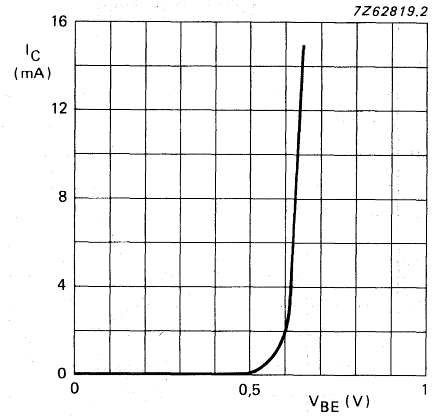


Fig. 5 V_{CE} = 5 V; T_j = 25 °C; typical values.

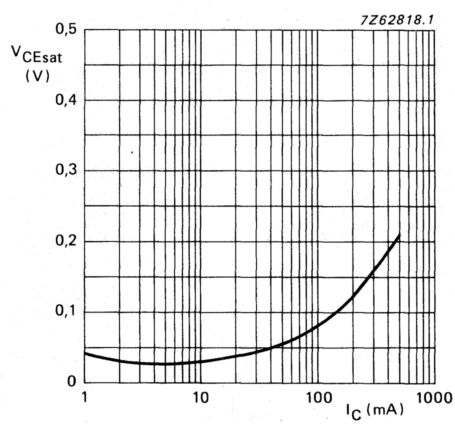


Fig. 6 I_C/I_B = 10; T_j = 25 °C; typical values.

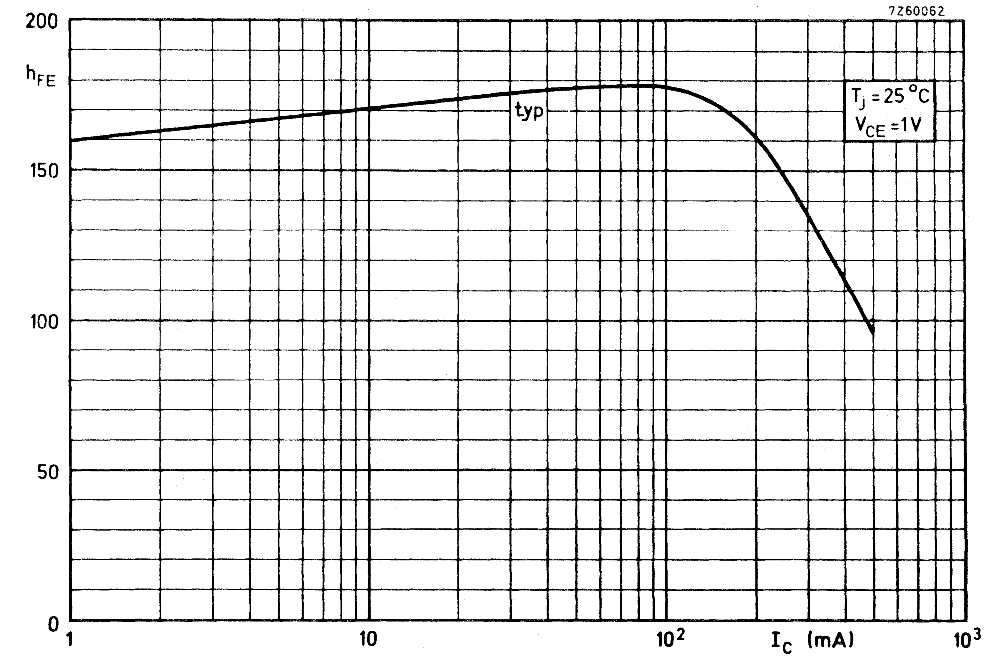

7Z60062
200
h_{FE}
150
100
50
0
1
10
10^2
I_C (mA)
10^3
typ
$T_j = 25\,^\circ C$
$V_{CE} = 1V$

Fig. 7.

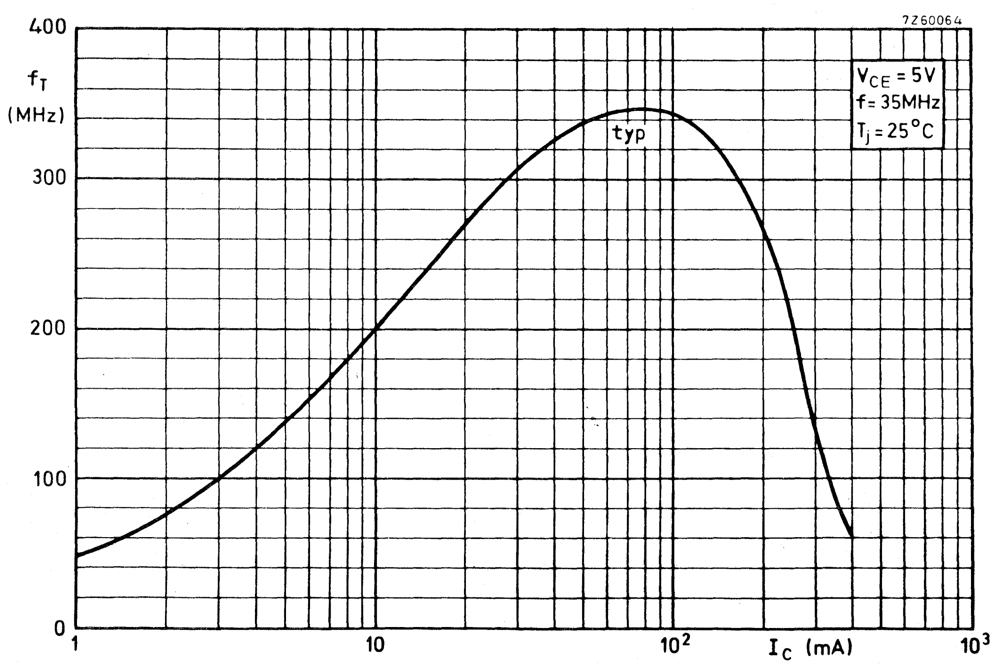

7Z60064
400
f_T
(MHz)
300
200
100
0
1
10
10^2
I_C (mA)
10^3
typ
$V_{CE} = 5V$
f = 35MHz
$T_j = 25\,^\circ C$

Fig. 8.

SILICON PLANAR EPITAXIAL TRANSISTORS

Medium power p-n-p transistors in a miniature plastic envelope intended for applications in thick and thin-film circuits. These transistors are intended for general purposes as well as for use in driver stages of audio amplifiers.

N-P-N complements are BCX54, BCX55 and BCX56 respectively.

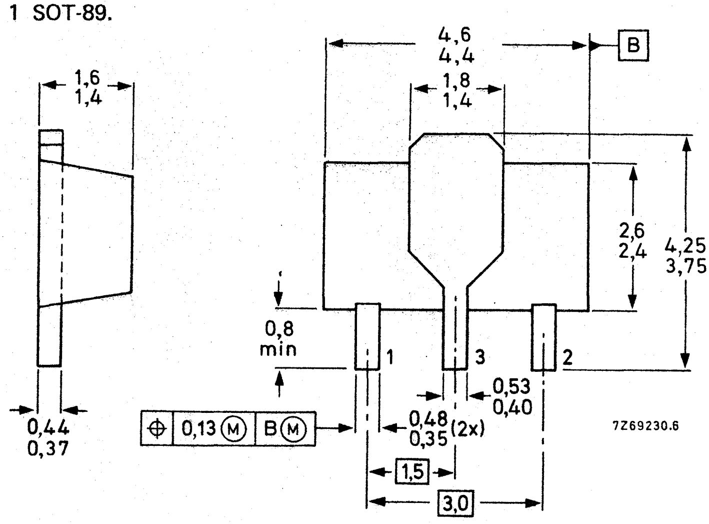
QUICK REFERENCE DATA

			BCX51	BCX52	BCX53	
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	45	60	100	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	45	60	80	V
Collector-emitter voltage (R_{BE} = 1 kΩ)	$-V_{CER}$	max.	45	60	100	V
Collector current (peak value)	$-I_{CM}$	max.		1,5		A
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.		1		W
Junction temperature	T_j	max.		150		°C
D.C. current gain $-I_C$ = 150 mA; $-V_{CE}$ = 2 V	h_{FE}			40 to 250		
Transition frequency at f = 35 MHz $-I_C$ = 10 mA; $-V_{CE}$ = 5 V	f_T	typ.		50		MHz

MECHANICAL DATA

Dimensions in mm

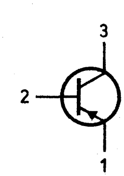
Fig. 1 SOT-89.



BOTTOM VIEW

Mark

BCX51	= AA
BCX51-6	= AB
BCX51-10	= AC
BCX51-16	= AD
BCX52	= AE
BCX52-6	= AF
BCX52-10	= AG
BCX52-16	= AM
BCX53	= AH
BCX53-6	= AJ
BCX53-10	= AK
BCX53-16	= AL



See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BCX51	BCX52	BCX53	
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	45	60	100	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	45	60	80	V
Collector-emitter voltage (R_{BE} = 1 kΩ)	$-V_{CER}$	max.	45	60	100	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5	5	5	V

Collector current (d.c.)	$-I_C$	max.	1,0	A
Collector current (peak value)	$-I_{CM}$	max.	1,5	A
Base current (d.c.)	$-I_B$	max.	0,1	A
Base current (peak value)	$-I_{BM}$	max.	0,2	A
Total power dissipation up to T_{amb} = 25 °C mounted on a ceramic substrate area = 2,5 cm²; thickness = 0,7 mm	P_{tot}	max.	1,0	W
Storage temperature	T_{stg}		−65 to +150	°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE

From junction to collector tab	$R_{th\ j\text{-}tab}$	=	10	K/W
From junction to ambient in free air mounted on a ceramic substrate area = 2,5 cm²; thickness = 0,7 mm	$R_{th\ j\text{-}a}$	=	125	K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Collector cut-off current				
$I_E = 0$; $-V_{CB} = 30$ V	$-I_{CBO}$	<	100	nA
$I_E = 0$; $-V_{CB} = 30$ V; $T_j = 125$ °C	$-I_{CBO}$	<	10	μA
Emitter cut-off current				
$I_C = 0$; $-V_{EB} = 5$ V	$-I_{EBO}$	<	10	μA
Base-emitter voltage				
$-I_C = 500$ mA; $-V_{CE} = 2$ V	$-V_{BE}$	<	1	V
Saturation voltage				
$-I_C = 500$ mA; $-I_B = 50$ mA	$-V_{CEsat}$	<	0,5	V
D.C. current gain				
$-I_C = 5$ mA; $-V_{CE} = 2$ V	h_{FE}	>	25	
$-I_C = 150$ mA; $-V_{CE} = 2$ V	h_{FE}		40 to 250	
$-I_C = 500$ mA; $-V_{CE} = 2$ V	h_{FE}	>	25	
Transition frequency at f = 35 MHz				
$-I_C = 10$ mA; $-V_{CE} = 5$ V	f_T	typ.	50	MHz

CHARACTERISTICS (continued)

			BCX51-6 52-6 53-6	BCX51-10 52-10 53-10	BCX51-16 52-16 53-16
D.C. current gain $-I_C$ = 150 mA; $-V_{CE}$ = 2 V	h_{FE}	>	40	63	100
		<	100	160	250

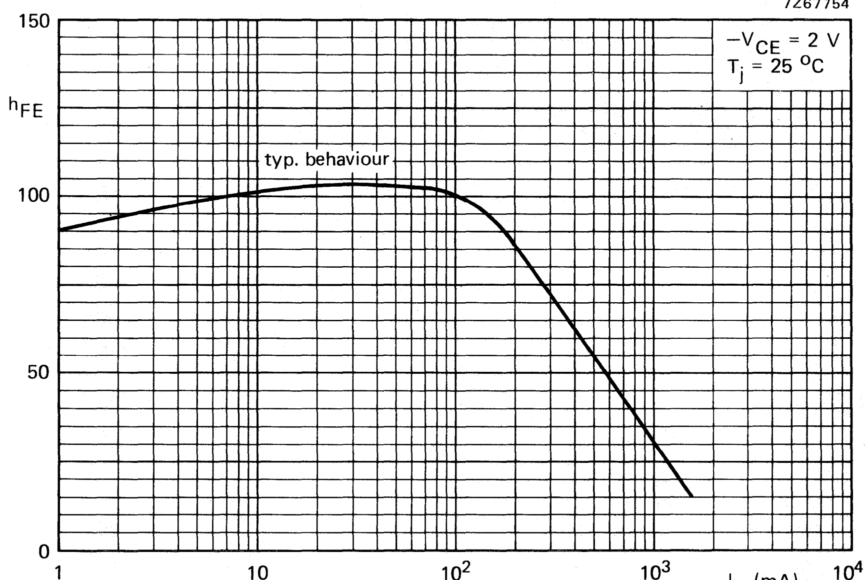


Fig. 2.

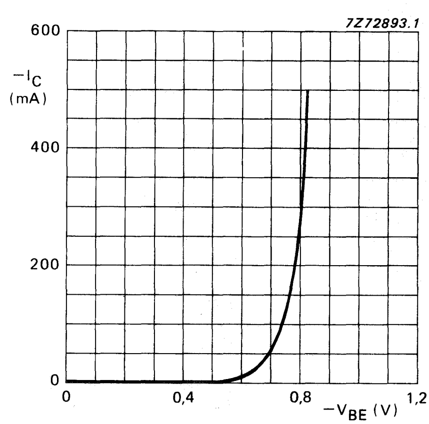


Fig. 3 $-V_{CE}$ = 2 V; T_j = 25 °C; typical values.

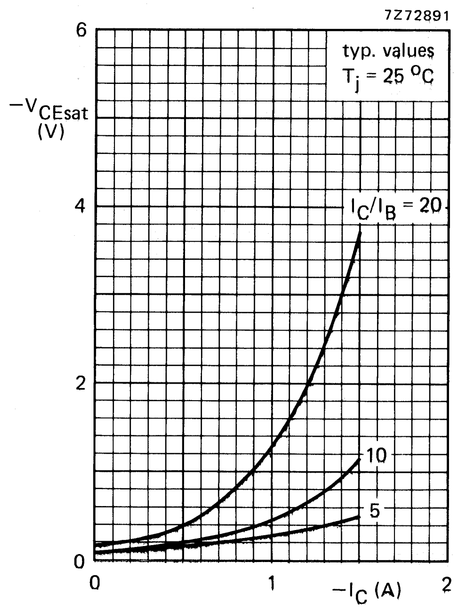


Fig. 4.

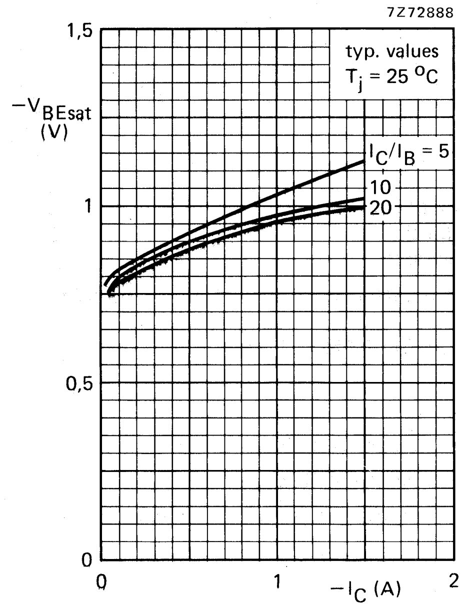


Fig. 5.

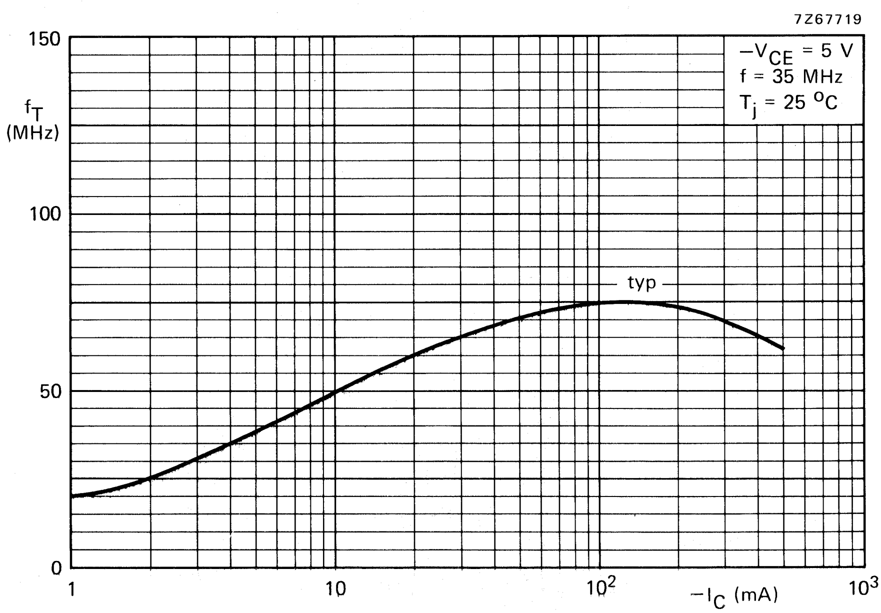


Fig. 6.

SILICON PLANAR EPITAXIAL TRANSISTORS

Medium power n-p-n transistors in a miniature plastic envelope intended for applications in thick and thin-film circuits. These transistors are intended for general purposes as well as for use in driver stages of audio amplifiers.

P-N-P complements are BCX51, BCX52 and BCX53 respectively.

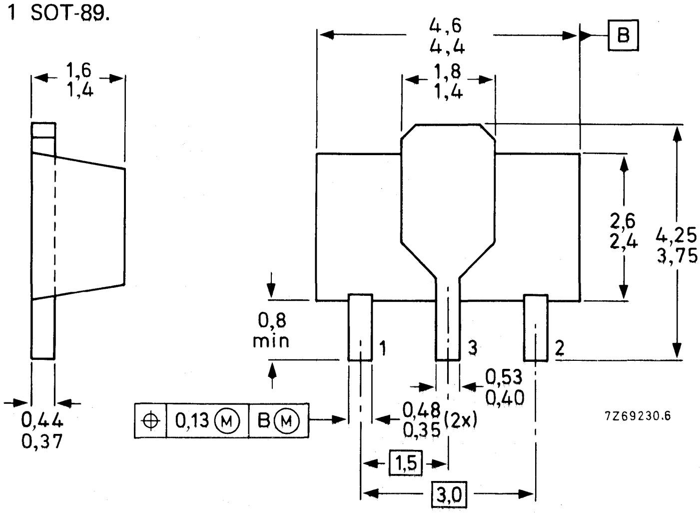
QUICK REFERENCE DATA

			BCX54	BCX55	BCX56	
Collector-base voltage (open emitter)	V_{CBO}	max.	45	60	100	V
Collector-emitter voltage (open base)	V_{CEO}	max.	45	60	80	V
Collector-emitter voltage (R_{BE} = 1 kΩ)	V_{CER}	max.	45	60	100	V
Collector current (peak value)	I_{CM}	max.		1,5		A
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.		1		W
Junction temperature	T_j	max.		150		°C
D.C. current gain I_C = 150 mA; V_{CE} = 2 V	h_{FE}			40 to 250		
Transition frequency at f = 35 MHz I_C = 10 mA; V_{CE} = 5 V	f_T	typ.		130		MHz

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-89.

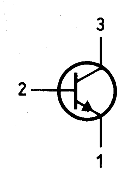


BOTTOM VIEW

See also *Soldering recommendations.*

Mark

BCX54	= BA
BCX54-6	= BB
BCX54-10	= BC
BCX54-16	= BD
BCX55	= BE
BCX55-6	= BF
BCX55-10	= BG
BCX55-16	= BM
BCX56	= BH
BCX56-6	= BJ
BCX56-10	= BK
BCX56-16	= BL



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BCX54	BCX55	BCX56	
Collector-base voltage (open emitter)	V_{CBO}	max.	45	60	100	V
Collector-emitter voltage (open base)	V_{CEO}	max.	45	60	80	V
Collector-emitter voltage (R_{BE} = 1 kΩ)	V_{CER}	max.	45	60	100	V
Emitter-base voltage (open collector)	V_{EBO}	max.	5	5	5	V
Collector current (d.c.)	I_C	max.		1,0		A
Collector current (peak value)	I_{CM}	max.		1,5		A
Base current (d.c.)	I_B	max.		0,1		A
Base current (peak value)	I_{BM}	max.		0,2		A
Total power dissipation up to T_{amb} = 25 °C mounted on a ceramic substrate area = 2,5 cm²; thickness = 0,7 mm	P_{tot}	max.		1,0		W
Storage temperature	T_{stg}			−65 to +150		°C
Junction temperature	T_j	max.		150		°C

THERMAL RESISTANCE

From junction to collector tab	$R_{th\ j\text{-}tab}$	=	10	K/W
From junction to ambient in free air mounted on a ceramic substrate area = 2,5 cm²; thickness = 0,7 mm	$R_{th\ j\text{-}a}$	=	125	K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Collector cut-off current				
I_E = 0; V_{CB} = 30 V	I_{CBO}	<	100	nA
I_E = 0; V_{CB} = 30 V; T_j = 125 °C	I_{CBO}	<	10	μA
Emitter cut-off current				
I_C = 0; V_{EB} = 5 V	I_{EBO}	<	10	μA
Base-emitter voltage				
I_C = 500 mA; V_{CE} = 2 V	V_{BE}	<	1	V
Saturation voltage				
I_C = 500 mA; I_B = 50 mA	V_{CEsat}	<	0,5	V
D.C. current gain				
I_C = 5 mA; V_{CE} = 2 V	h_{FE}	>	25	
I_C = 150 mA; V_{CE} = 2 V	h_{FE}		40 to 250	
I_C = 500 mA; V_{CE} = 2 V	h_{FE}	>	25	
Transition frequency at f = 35 MHz				
I_C = 10 mA; V_{CE} = 5 V	f_T	typ.	130	MHz

CHARACTERISTICS (continued)

			BXC54-6 55-6 56-6	BCX54-10 55-10 56-10	BCX54-16 55-16 56-16
D.C. current gain I_C = 150 mA; V_{CE} = 2 V	h_{FE}	> <	40 100	63 160	100 250

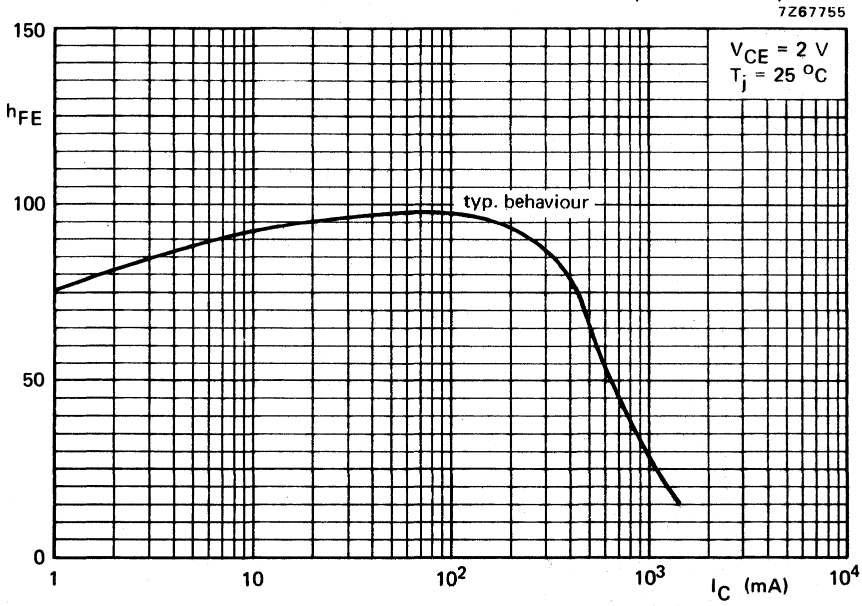


Fig. 2.

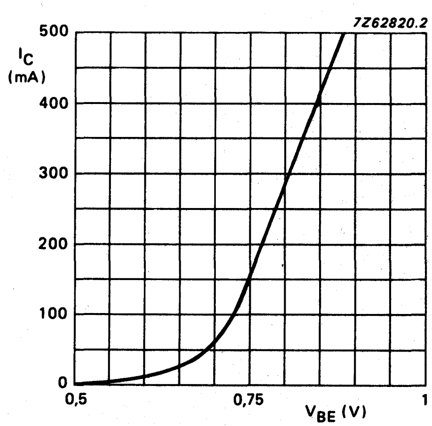


Fig. 3 V_{CE} = 2 V; T_j = 25 °C; typical values.

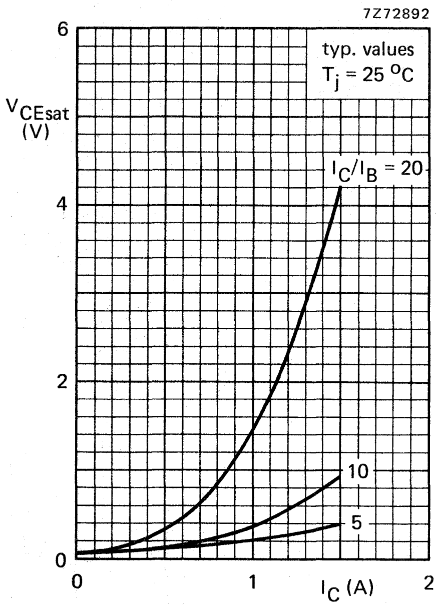


Fig. 4.

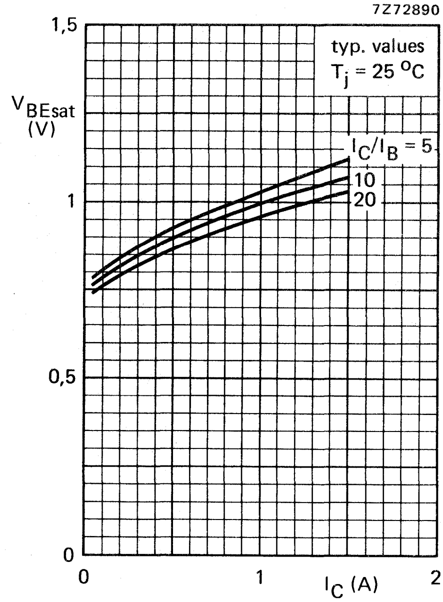


Fig. 5.

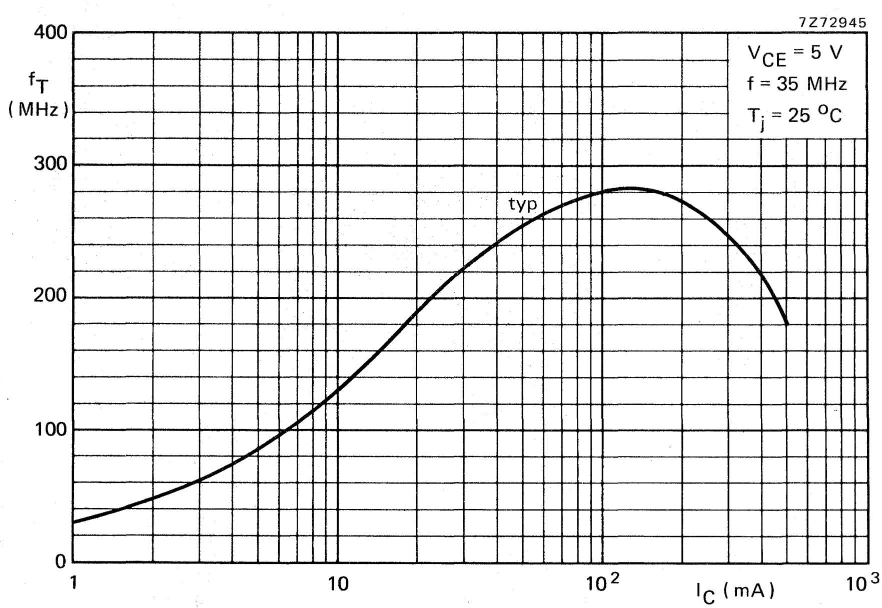


Fig. 6.

SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N silicon transistors, in a microminiature plastic envelope, intended for low level, low noise, low frequency purpose applications in hybrid circuits.

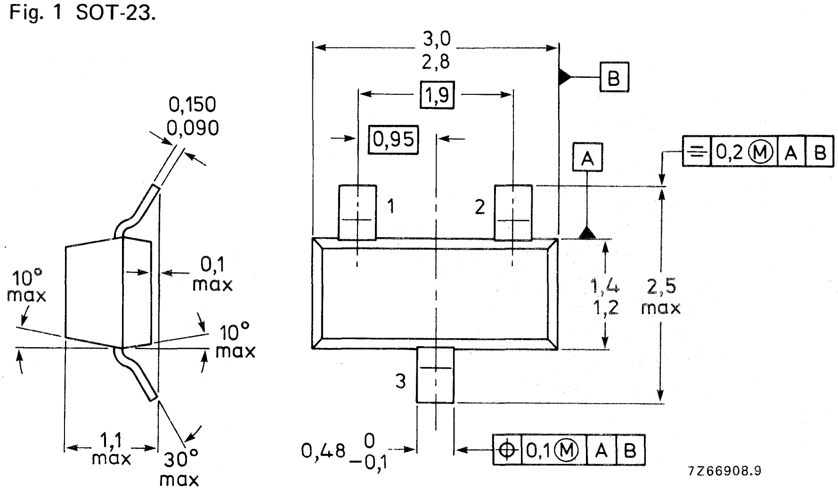
QUICK REFERENCE DATA

Collector-emitter voltage ($V_{BE} = 0$)	V_{CES}	max.	45	V
Collector-emitter voltage (open base)	V_{CEO}	max.	45	V
Collector current (d.c.)	I_C	max.	200	mA
Total power dissipation	P_{tot}	max.	150	mW
Junction temperature	T_j	max.	150	°C
Transition frequency at f = 100 MHz $V_{CE} = 5$ V; $I_C = 10$ mA	f_T	typ.	250	MHz
Noise figure at f = 1 kHz $V_{CE} = 5$ V; $I_C = 200$ μA; B = 200 Hz	F	typ.	2	dB

MECHANICAL DATA

Dimensions in mm

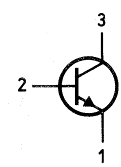
Fig. 1 SOT-23.



TOP VIEW

Marking code

BCX70G = AG
BCX70H = AH
BCX70J = AJ
BCX70K = AK



See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-emitter voltage (V_{BE} = 0)	V_{CES}	max.	45	V
Collector-emitter voltage (open base)	V_{CEO}	max.	45	V
Emitter-base voltage (open collector)	V_{EBO}	max.	5	V
Collector current (d.c.)	I_C	max.	200	mA
Base current	I_B	max.	50	mA
Total power dissipation up to T_{amb} = 100 °C**	P_{tot}	max.	150	mW
Storage temperature	T_{stg}	−55 to + 125		°C
Junction temperature	T_j	max.	150	°C

THERMAL CHARACTERISTICS*

$T_j = Px\,(R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	50	K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280	K/W
From soldering points to ambient**	$R_{th\ s\text{-}a}$	=	90	K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Collector-emitter cut-off current				
V_{BE} = 0; V_{CE} = 45 V	I_{CES}	<	20	nA
V_{BE} = 0; V_{CE} = 45 V; T_{amb} = 150 °C	I_{CES}	<	20	μA
Emitter-base cut-off current				
I_C = 0; V_{EB} = 4 V	I_{EBO}	<	20	nA
Saturation voltages				
at I_C = 10 mA; I_B = 0,25 mA	V_{CEsat}	0,05 to 0,35		V
	V_{BEsat}	0,6 to 0,85		V
at I_C = 50 mA; I_B = 1,25 mA	V_{CEsat}	0,1 to 0,55		V
	V_{BEsat}	0,7 to 1,05		V
Transition frequency at f = 100 MHz▲				
I_C = 10 mA; V_{CE} = 5 V	f_T	>	125	MHz
		typ.	250	MHz
Collector capacitance at f = 1 MHz				
→ $I_E = I_e$ = 0; V_{CB} = 10 V	C_c	typ.	2,5	pF
Emitter capacitance at f = 1 MHz				
$I_C = I_c$ = 0; V_{EB} = 0,5 V	C_e	typ.	8	pF
Noise figure at R_S = 2 kΩ				
I_C = 200 μA; V_{CE} = 5 V; f = 1 kHz; B = 200 Hz	F	typ.	2	dB
		<	6	dB

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

▲ Measured under pulse conditions.

			G	H	J	K		
D.C. current gain								
V_{CE} = 5 V; I_C = 10 μA	h_{FE}	typ.	78	145	220	300		
		>	–	20	40	100		
V_{CE} = 5 V; I_C = 2 mA	h_{FE}	>	120	180	250	380		
		typ.	170	250	350	500		
		<	220	310	460	630		
V_{CE} = 1 V; I_C = 50 mA	h_{FE}	>	50	70	90	100		
Input impedance								
V_{CE} = 5 V; I_C = 2 mA; f = 1 kHz	h_{ie}	typ.	2,7	3,6	4,5	7,5	kΩ	←
Reverse voltage transfer ratio								
V_{CE} = 5 V; I_C = 2 mA; f = 1 kHz	h_{re}	typ.	1,5	2	2	3	10^{-4}	
Small-signal current gain								
V_{CE} = 5 V; I_C = 2 mA; f = 1 kHz	h_{fe}	typ.	200	260	330	520		←
Output admittance								
V_{CE} = 5 V; I_C = 2 mA; f = 1 kHz	h_{oe}	typ.	18	24	30	50	μS	←
Base-emitter voltage								
V_{CE} = 5 V; I_C = 2 mA	V_{BE}		0,55 to 0,75				V	
		typ.	0,65				V	
V_{CE} = 5 V; I_C = 10 μA	V_{BE}	typ.	0,52				V	
V_{CE} = 1 V; I_C = 50 mA	V_{BE}	typ.	0,78				V	

Switching times

I_{Con} = 10 mA; I_{Bon} = $-I_{Boff}$ = 1 mA
V_{CC} = 10 V; R_L = 990 Ω

turn-on time ($t_d + t_r$)	t_{on}	typ.	85	ns
		<	150	ns
turn-off time ($t_s + t_f$)	t_{off}	typ.	480	ns
		<	800	ns

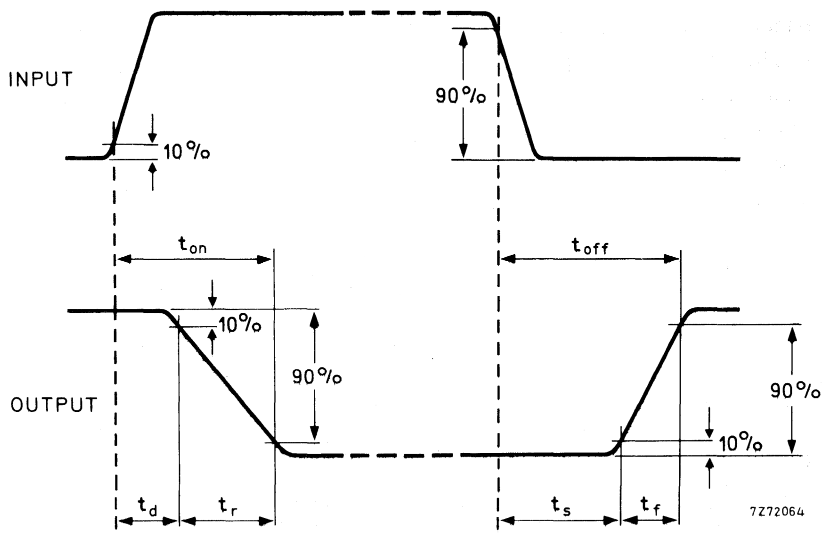


Fig. 2 Switching waveforms.

SILICON PLANAR EPITAXIAL TRANSISTORS

P-N-P silicon transistors, in a microminiature plastic envelope, intended for low level, low noise, low frequency purpose applications in hybrid circuits.

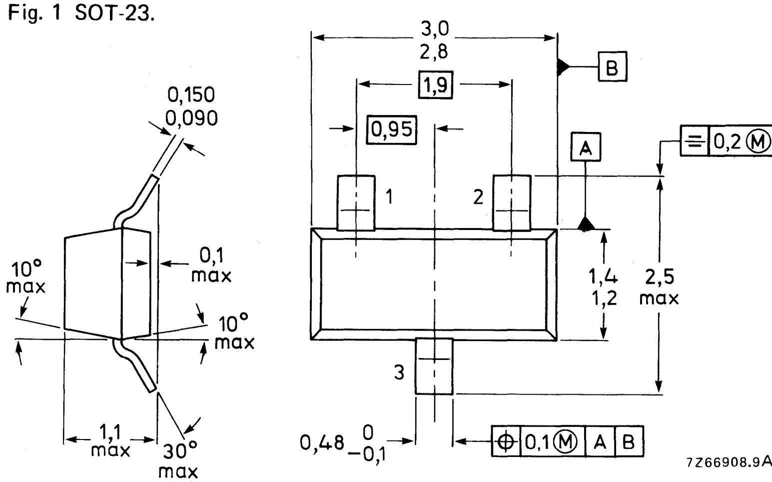
QUICK REFERENCE DATA

Collector-emitter voltage (V_{BE} = 0)	$-V_{CES}$	max.	45	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	45	V
Collector current (d.c.)	$-I_C$	max.	200	mA
Total power dissipation	P_{tot}	max.	150	mW
Junction temperature	T_j	max.	150	°C
Transition frequency at f = 100 MHz $-V_{CE}$ = 5 V; $-I_C$ = 10 mA	f_T	typ.	180	MHz
Noise figure at f = 1 kHz $-V_{CE}$ = 5 V; $-I_C$ = 200 μA	F	typ.	2	dB

MECHANICAL DATA

Dimensions in mm

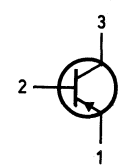
Fig. 1 SOT-23.



TOP VIEW

Marking code

BCX71G = BG
BCX71H = BH
BCX71J = BJ
BCX71K = BK



See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-emitter voltage (V_{BE} = 0)	$-V_{CES}$	max.	45 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	45 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5 V
Collector current (d.c.)	$-I_C$	max.	200 mA
Base current	$-I_B$	max.	50 mA
Total power dissipation up to T_{amb} = 100 °C**	P_{tot}	max.	150 mW
Storage temperature	T_{stg}	−55 to + 125 °C	
Junction temperature	T_j	max.	150 °C

THERMAL CHARACTERISTICS*

$T_j = P\text{x} (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	50 K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280 K/W
From soldering points to ambient**	$R_{th\ s\text{-}a}$	=	90 K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Collector-emitter cut-off current			
V_{EB} = 0; $-V_{CE}$ = 45 V	$-I_{CES}$	<	20 nA
V_{EB} = 0; $-V_{CE}$ = 45 V; T_{amb} = 150 °C	$-I_{CES}$	<	20 μA
Emitter-base cut-off current			
I_C = 0; $-V_{EB}$ = 4 V	$-I_{EBO}$	<	20 nA
Saturation voltages			
$-I_C$ = 10 mA; $-I_B$ = 0,25 mA	$-V_{CEsat}$	0,06 to 0,25 V	
	$-V_{BEsat}$	0,6 to 0,85 V	
$-I_C$ = 50 mA; $-I_B$ = 1,25 mA	$-V_{CEsat}$	0,12 to 0,55 V	
	$-V_{BEsat}$	0,68 to 1,05 V	
Transition frequency at f = 100 MHz▲			
$-V_{CE}$ = 5 V; $-I_C$ = 10 mA	f_T	typ.	180 MHz
Collector capacitance at f = 1 MHz			
→ $-V_{CB}$ = 10 V; $I_E = I_e$ = 0	C_c	typ.	4,5 pF
Emitter capacitance at f = 1 MHz			
$-V_{EB}$ = 0,5 V; $I_C = I_c$ = 0	C_e	typ.	11 pF
Noise figure at R_S = 2 kΩ			
$-V_{CE}$ = 5 V; $-I_C$ = 200 μA; B = 200 Hz	F	typ.	2 dB
		<	6 dB

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

▲ Measured under pulse conditions.

			G	H	J	K	
D.C. current gain							
$-V_{CE}$ = 5 V; $-I_C$ = 10 μA	h_{FE}	typ.	140	200	270	340	
		>	—	30	40	100	
		>	120	180	250	380	
$-V_{CE}$ = 5 V; $-I_C$ = 2 mA	h_{FE}	typ.	170	250	350	500	
		<	220	310	460	630	
$-V_{CE}$ = 1 V; $-I_C$ = 50 mA	h_{FE}	>	60	80	100	110	
Input impedance							
$-V_{CE}$ = 5 V; $-I_C$ = 2 mA; f = 1 kHz	h_{ie}	typ.	2,7	3,6	4,5	7,5	kΩ
Reverse voltage transfer ratio							
$-V_{CE}$ = 5 V; $-I_C$ = 2 mA; f = 1 kHz	h_{re}	typ.	1,5	2	2	3	10^{-4}
Small-signal current gain							
$-V_{CE}$ = 5 V; $-I_C$ = 2 mA; f = 1 kHz	h_{fe}	typ.	200	260	330	520	
Output admittance							
$-V_{CE}$ = 5 V; $-I_C$ = 2 mA; f = 1 kHz	h_{oe}	typ.	18	24	30	50	μS ←
Base-emitter voltage							
$-V_{CE}$ = 5 V; $-I_C$ = 2 mA	V_{BE}		0,6 to 0,75				V
		typ.	0,65				V
$-V_{CE}$ = 5 V; $-I_C$ = 10 μA	V_{BE}	typ.	0,55				V
$-V_{CE}$ = 1 V; $-I_C$ = 50 mA	V_{BE}	typ.	0,72				V

Switching times

$-I_{Con}$ = 10 mA; $-I_{Bon}$ = I_{Boff} = 1 mA
$-V_{CC}$ = 10 V; R_L = 990 Ω

turn-on time ($t_d + t_r$)	t_{on}	typ.	85	ns
		<	150	ns
turn-off time ($t_s + t_f$)	t_{off}	typ.	480	ns
		<	800	ns

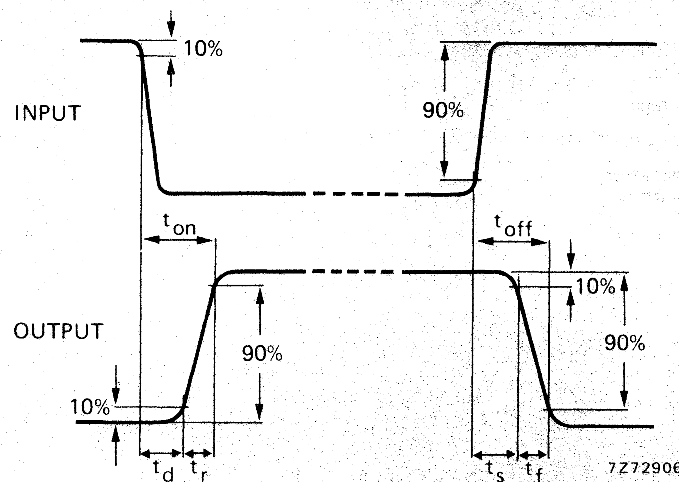


Fig. 2 Switching waveforms.

N-CHANNEL SILICON FIELD-EFFECT TRANSISTORS

Asymmetrical N-channel planar epitaxial junction field-effect transistors in the miniature plastic envelope intended for applications up to the v.h.f. range in hybrid thick and thin-film circuits. Special features are the low feedback capacitance and the low noise figure. These features make the product very suitable for applications such as the r.f. stages in f.m. portables (BF510), car radios (BF511) and mains radios (BF512) or the mixer stage (BF513).

QUICK REFERENCE DATA

Drain-source voltage	V_{DS}	max.		20			V
Drain current (d.c. or average)	I_D	max.		30			mA
Total power dissipation up to T_{amb} = 65 °C	P_{tot}	max.		250			mW
			BF510	511	512	513	
Drain current V_{DS} = 10 V; V_{GS} = 0	I_{DSS}	>	0,7	2,5	6	10	mA
		<	3,0	7,0	12	18	mA
Transfer admittance (common source) V_{DS} = 10 V; V_{GS} = 0; f = 1 kHz	$\|y_{fs}\|$	>	2,5	4	6	7	mS
Feedback capacitance V_{DS} = 10 V; V_{GS} = 0	C_{rs}	typ.	0,3	0,3	–	–	pF
V_{DS} = 10 V; I_D = 5 mA	C_{rs}	typ.	–	–	0,3	0,3	pF
Noise figure at optimum source admittance G_S = 1 mS; $-B_S$ = 3 mS; f = 100 MHz							
V_{DS} = 10 V; V_{GS} = 0	F	typ.	1,5	1,5	–	–	dB
V_{DS} = 10 V; I_D = 5 mA	F	typ.	–	–	1,5	1,5	dB

MECHANICAL DATA

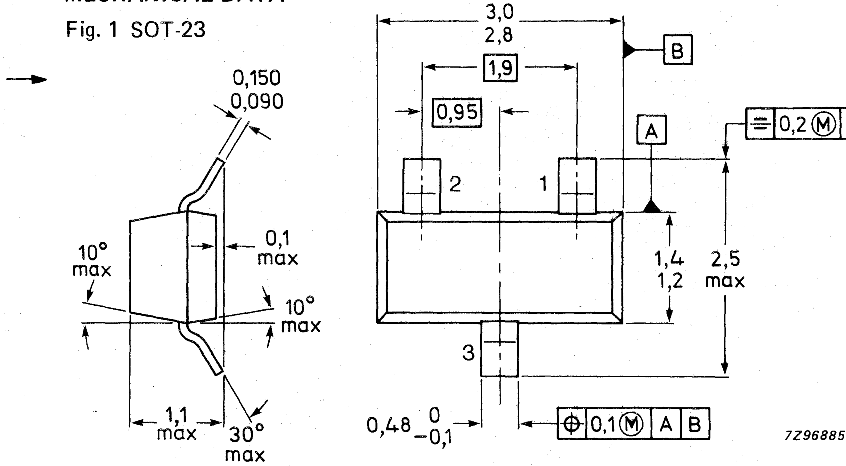
SOT-23.

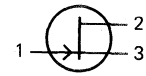
See also *Soldering recommendations*.

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-23





Marking code

BF510 = S6
BF511 = S7
BF512 = S8
BF513 = S9

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage see Fig. 4	V_{DS}	max.	20	V
Drain-gate voltage (open source) see Fig. 4	V_{DGO}	max.	20	V
Drain current (d.c. or average)	I_D	max.	30	mA
Gate current	$\pm I_G$	max.	10	mA
Total power dissipation up to T_{amb} = 60 °C**	P_{tot}	max.	250	mW
Storage temperature range	T_{stg}	−65 to + 175		°C
Junction temperature	T_j	max.	175	°C

THERMAL CHARACTERISTICS*

$T_j = Px\,(R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	60	K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280	K/W
From soldering points to ambient**	$R_{th\ s\text{-}a}$	=	90	K/W

* See *Thermal characteristics.*
** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

STATIC CHARACTERISTICS

T_{amb} = 25 °C

			BF510	511	512	513
Gate cut-off current $-V_{GS}$ = 0,2 V; V_{DS} = 0	$-I_{GSS}$	<	10	10	10	10 nA
Gate-drain breakdown voltage I_S = 0; $-I_D$ = 10 μA	$-V_{(BR)GDO}$	>	20	20	20	20 V
Drain current V_{DS} = 10 V; V_{GS} = 0	I_{DSS}	>	0,7	2,5	6	10 mA
		<	3,0	7,0	12	18 mA
Gate-source cut-off voltage I_D = 10 μA; V_{DS} = 10 V	$-V_{(P)GS}$	typ.	0,8	1,5	2,2	3 V

DYNAMIC CHARACTERISTICS

Measuring conditions (common source): V_{DS} = 10 V; V_{GS} = 0; T_{amb} = 25 °C for BF510 and BF511
V_{DS} = 10 V; I_D = 5 mA; T_{amb} = 25 °C for BF512 and BF513

y-parameters (common source)			BF510	511	512	513
Input capacitance at f = 1 MHz	C_{is}	<	5	5	5	5 pF
Input conductance at f = 100 MHz	g_{is}	typ.	100	90	60	50 μS
Feedback capacitance at f = 1 MHz	C_{rs}	typ.	0,3	0,3	0,3	0,3 pF
		<	0,4	0,4	0,4	0,4 pF
Transfer admittance at f = 1 kHz	$\|y_{fs}\|$	>	2,5	4,0	4,0	3,5 mS
V_{GS} = 0 instead of I_D = 5 mA	$\|y_{fs}\|$	>	–	–	6,0	7,0 mS
Transfer admittance at f = 100 MHz	$\|y_{fs}\|$	typ.	3,5	5,5	5,0	5,0 mS
Output capacitance at f = 1 MHz	C_{os}	<	3	3	3	3 pF
Output conductance at f = 1 MHz	g_{os}	<	60	80	100	120 μS
Output conductance at f = 100 MHz	g_{os}	typ.	35	55	70	90 μS
Noise figure at optimum source admittance G_S = 1 mS; $-B_S$ = 3 mS; f = 100 MHz	F	typ.	1,5	1,5	1,5	1,5 dB

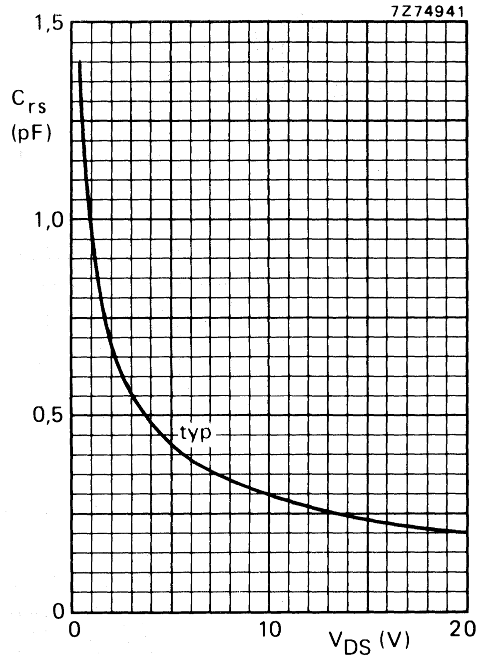


Fig. 2 V_{GS} = 0 for BF510 and BF511; I_D = 5 mA for BF512 and BF513; f = 1 MHz; T_{amb} = 25 °C.

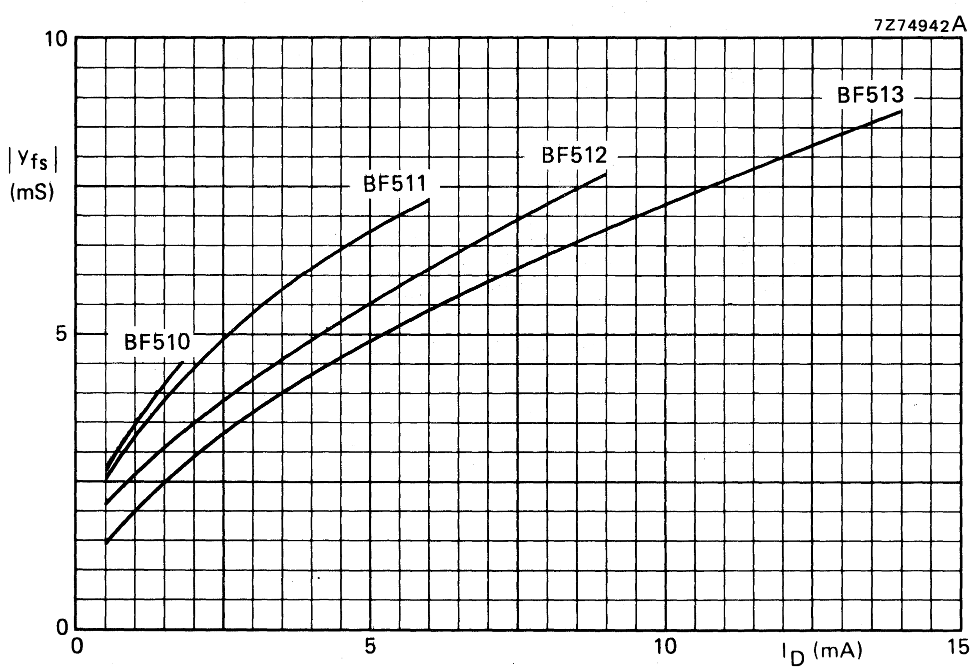


Fig. 3 V_{DS} = 10 V; f = 1 kHz; T_{amb} = 25 °C; typical values.

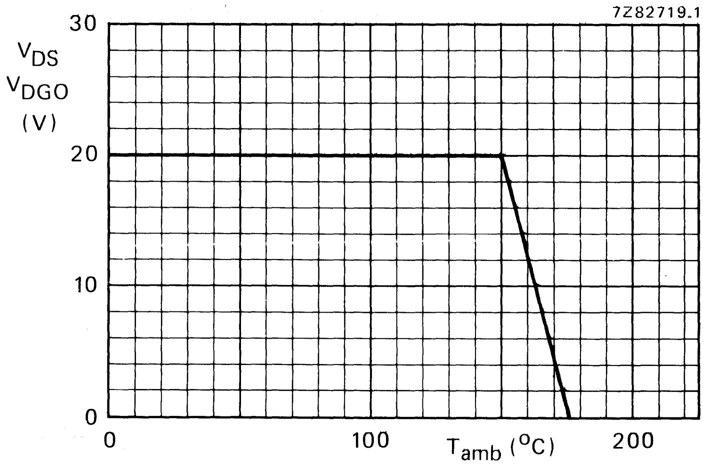


Fig. 4 Voltage derating curve.

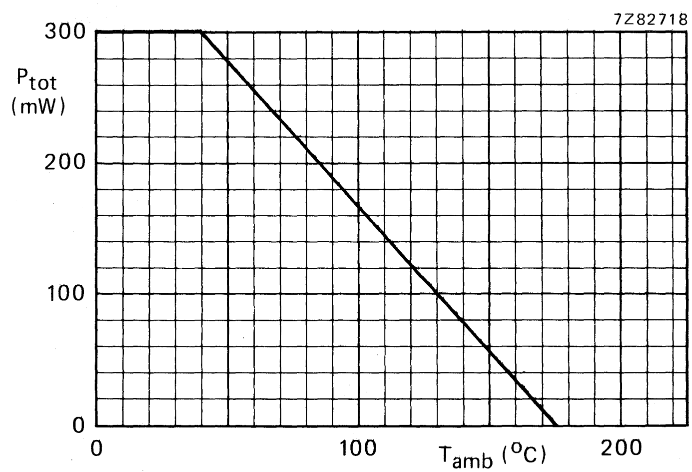


Fig. 5 Power derating curve.

SILICON PLANAR TRANSISTOR

P-N-P transistor in a microminiature plastic envelope. Primarily intended for use as mixer in v.h.f. tuners. Also suitable as r.f. amplifier and oscillator in f.m. tuners.

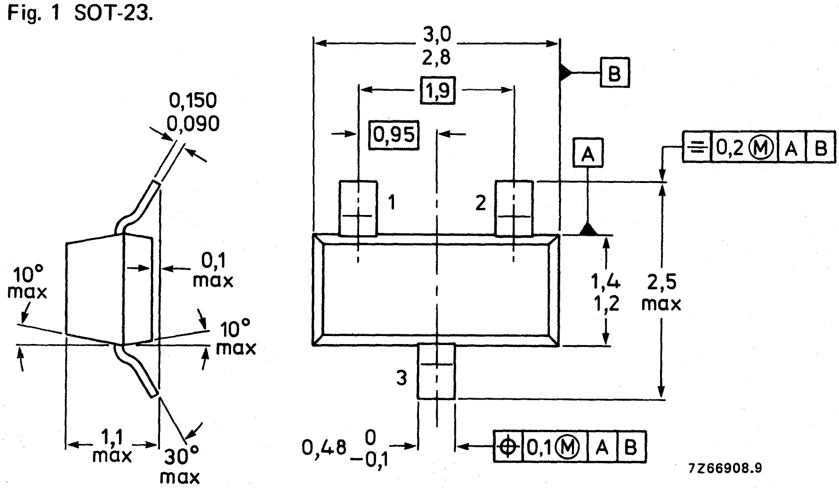
QUICK REFERENCE DATA

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	30	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	30	V
Collector current (d.c.)	$-I_C$	max.	25	mA
Total power dissipation up to T_{amb} = 60 °C	P_{tot}	max.	200	mW
Junction temperature	T_j	max.	150	°C
D.C. current gain I_E = 1 mA; $-V_{CB}$ = 10 V	h_{FE}	>	25	
Transition frequency at f = 100 MHz I_E = 1 mA; $-V_{CB}$ = 10 V	f_T	typ.	350	MHz
Noise figure at f = 200 MHz I_E = 1 mA; $-V_{CB}$ = 10 V	F	typ.	5	dB

MECHANICAL DATA

Dimensions in mm

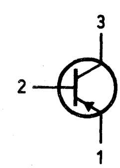
Fig. 1 SOT-23.



TOP VIEW

Marking code

BF536 = G3



See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	30	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	30	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	4	V
Collector current (d.c.)	$-I_C$	max.	25	mA
Total power dissipation up to T_{amb} = 60 °C **	P_{tot}	max.	200	mW
Storage temperature	T_{stg}	−65 to + 150		°C
Junction temperature	T_j	max.	150	°C

THERMAL CHARACTERISTICS*

$T_j = P\,(R_{th\,j\text{-}t} + R_{th\,t\text{-}s} + R_{th\,s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\,j\text{-}t}$	=	60	K/W
From tab to soldering points	$R_{th\,t\text{-}s}$	=	280	K/W
From soldering points to ambient**	$R_{th\,s\text{-}a}$	=	90	K/W

CHARACTERISTICS

T_{amb} = 25 °C; unless otherwise specified

Collector cut-off current $I_E = 0$; $-V_{CB} = 20$ V	$-I_{CBO}$	<	50	nA
D.C. current gain $I_E = 1$ mA; $-V_{CB} = 10$ V	h_{FE}	>	25	
Transition frequency at f = 100 MHz $I_E = 1$ mA; $-V_{CB} = 10$ V	f_T	typ.	350	MHz
Noise figure at f = 200 MHz $I_E = 1$ mA; $-V_{CB} = 10$ V; $R_S = 50\ \Omega$	F	typ.	5	dB
Transducer gain (common base) at f = 200 MHz $I_E = 3$ mA; $-V_{CB} = 10$ V; $R_S = 60\ \Omega$; $R_L = 920\ \Omega$	G_{tr}	typ.	17,5	dB

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

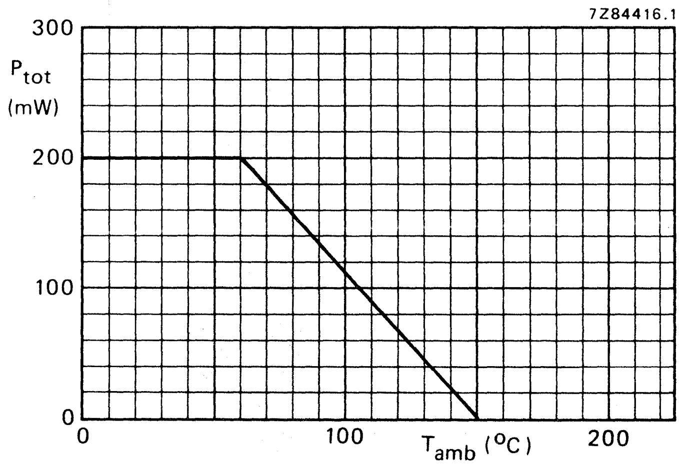


Fig. 2 Power derating curve.

SILICON PLANAR EPITAXIAL TRANSISTOR

P-N-P transistor, in a microminiature plastic envelope, intended for applications in thick and thin-film circuits. This transistor is primarily intended for use in i.f. detection applications.

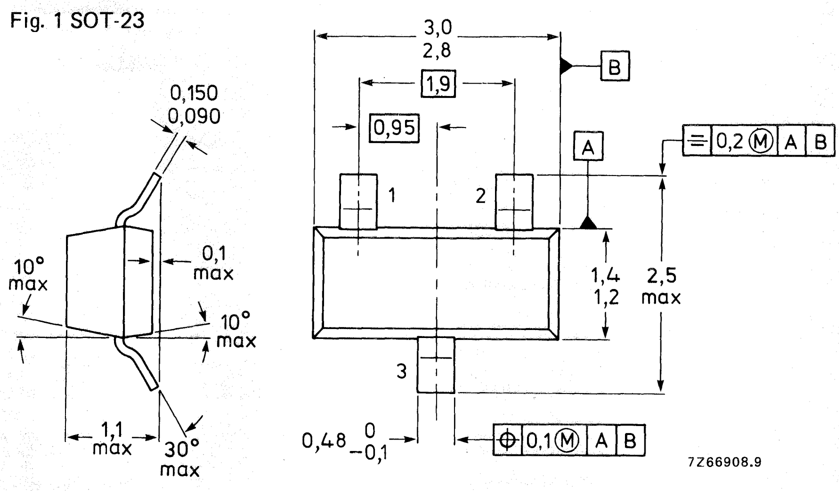
QUICK REFERENCE DATA

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	40	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	40	V
Collector current (d.c.)	$-I_C$	max.	25	mA
Total power dissipation up to T_{amb} = 60 °C	P_{tot}	max.	200	mW
Junction temperature	T_j	max.	150	°C
D.C. current gain at T_j = 25 °C $-I_C$ = 1 mA; $-V_{CE}$ = 10 V	h_{FE}	>	50	
Transition frequency at f = 100 MHz $-I_C$ = 1 mA; $-V_{CE}$ = 10 V	f_T	typ.	325	MHz
Noise figure at R_S = 300 Ω $-I_C$ = 1 mA; $-V_{CE}$ = 10 V; f = 100 kHz	F	typ.	2	dB

MECHANICAL DATA

Dimensions in mm

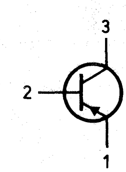
Fig. 1 SOT-23



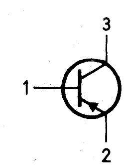
TOP VIEW

Marking code

BF550 = G2



BF550R = G5



See also *Soldering Recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	40 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	40 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	4 V
Collector current (d.c.)	$-I_C$	max.	25 mA
Total power dissipation up to T_{amb} = 60 °C **	P_{tot}	max.	200 mW
Storage temperature	T_{stg}		−55 to +150 °C
Junction temperature	T_j	max.	150 °C

THERMAL CHARACTERISTICS*

$T_j = Px\,(R_{th\,j\text{-}t} + R_{th\,t\text{-}s} + R_{th\,s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\,j\text{-}t}$	=	60 K/W
From tab to soldering points	$R_{th\,t\text{-}s}$	=	280 K/W
From soldering points to ambient**	$R_{th\,s\text{-}a}$	=	90 K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Collector cut-off current $I_E = 0$; $-V_{CB} = 30$ V	$-I_{CBO}$	<	50 nA
Emitter cut-off current $I_C = 0$; $-V_{EB} = 3$ V	$-I_{EBO}$	<	100 μA
Base-emitter voltage $-I_C = 1$ mA; $-V_{CE} = 10$ V	$-V_{BE}$	typ.	750 mV
D.C. current gain $-I_C = 1$ mA; $-V_{CE} = 10$ V	h_{FE}	>	50
Transition frequency at f = 100 MHz $-I_C = 1$ mA; $-V_{CE} = 10$ V	f_T	typ.	325 MHz
Feedback capacitance at f = 1 MHz $-I_C = 1$ mA; $-V_{CE} = 10$ V	C_{re}	typ.	0,5 pF
Noise figure at $R_S = 300\ \Omega$ $-I_C = 1$ mA; $-V_{CE} = 10$ V; f = 100 kHz	F	typ.	2 dB

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

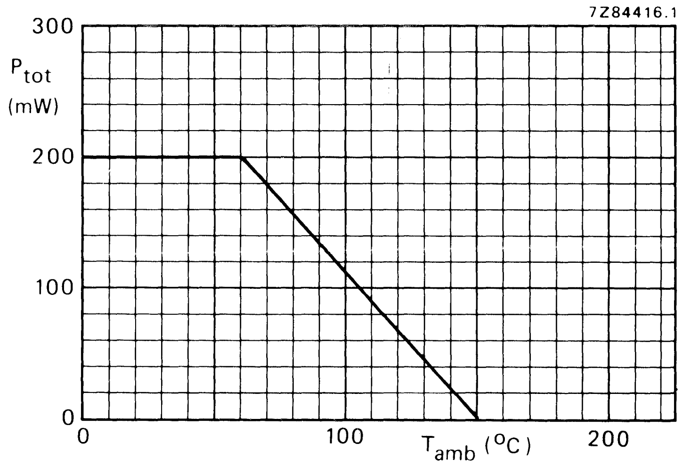


Fig. 2 Power derating curve.

SILICON PLANAR EPITAXIAL TRANSISTOR

P-N-P transistor in a microminiature plastic envelope, intended for applications in thick and thin-film circuits such as self-oscillating mixer in u.h.f. tuners in conjunction with bipolar transistors or with MOS fets.

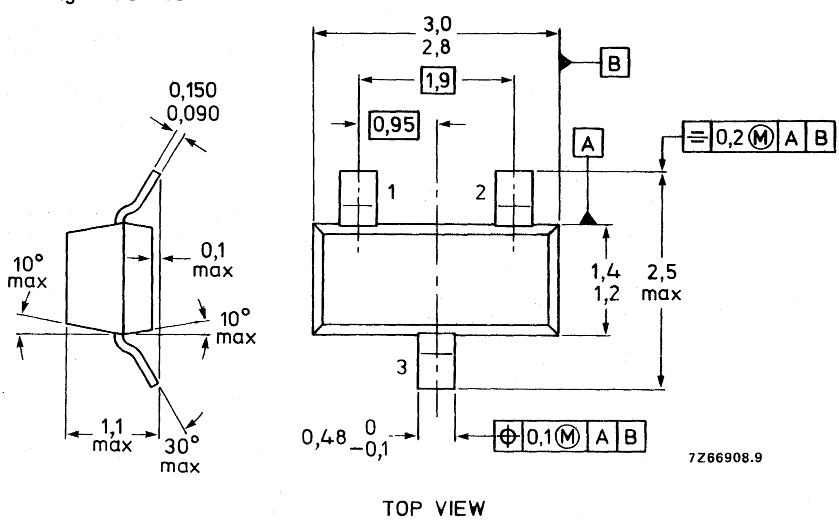
QUICK REFERENCE DATA

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	40	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	35	V
Collector current (d.c)	$-I_C$	max.	30	mA
Total power dissipation up to T_{amb} = 60 °C	P_{tot}	max.	200	mW
Junction temperature	T_j	max.	150	°C
Transition frequency at f = 100 MHz I_E = 3 mA; $-V_{CB}$ = 10 V	f_T	typ.	900	MHz

MECHANICAL DATA

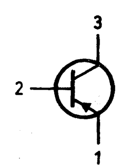
Dimensions in mm

Fig. 1 SOT-23



Marking code

BF569 = G6



See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	40 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	35 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	3 V
Collector current (d.c.)	$-I_C$	max.	30 mA
Total power dissipation up to T_{amb} = 60 °C**	P_{tot}	max.	200 mW
Storage temperature	T_{stg}		−65 to + 150 °C
Junction temperature	T_j	max.	150 °C

THERMAL CHARACTERISTICS*

$T_j = P \times (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	60 K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280 K/W
From soldering points to ambient**	$R_{th\ s\text{-}a}$	=	90 K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

Collector cut-off current $I_E = 0$; $-V_{CB} = 20$ V	$-I_{CBO}$	<	100 nA
D.C. current gain $I_E = 3$ mA; $-V_{CB} = 10$ V	h_{FE}	> typ.	25 50
Transition frequency at f = 100 MHz $I_E = 3$ mA; $-V_{CB} = 10$ V	f_T	typ.	900 MHz
Feedback capacitance at f = 1 MHz $I_E = 1$ mA; $-V_{CB} = 10$ V	C_{re}	typ.	0,33 pF
Noise figure at f = 800 MHz $I_E = 3$ mA; $-V_{CB} = 10$ V; $R_S = 60\ \Omega$; $R_L = 500\ \Omega$	F	typ.	4,5 dB
Power gain at f = 800 MHz $I_E = 3$ mA; $-V_{CB} = 10$ V; $R_S = 60\ \Omega$; $R_L = 500\ \Omega$	G_{pb}	typ.	14,5 dB

* See *Thermal characteristics.*
** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

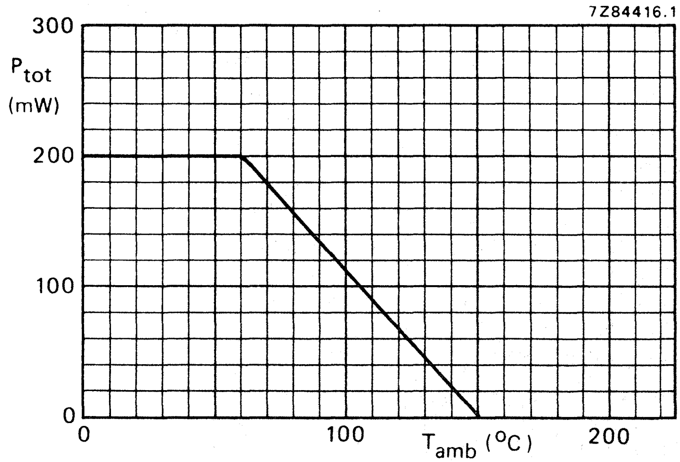


Fig. 2 Power derating curve.

SILICON PLANAR EPITAXIAL TRANSISTOR

N-P-N transistor in a plastic SOT-23 variant envelope, intended for use in large-signal handling i.f. pre-amplifiers of TV receivers in combination with surface acoustic wave filters.

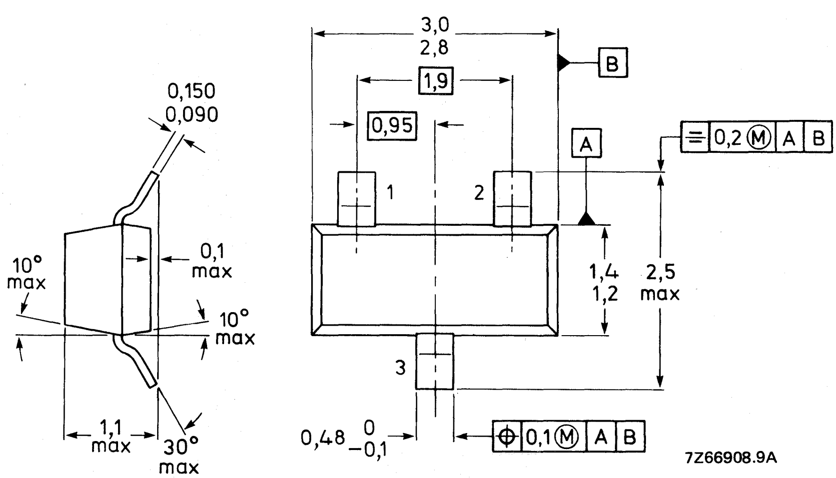
QUICK REFERENCE DATA

Collector-base voltage (open emitter)	V_{CBO}	max.	40	V
Collector-emitter voltage (open base)	V_{CEO}	max.	15	V
Collector current (d.c.)	I_C	max.	100	mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300	mW
Junction temperature	T_j	max.	150	°C
D.C. current gain I_C = 10 mA; V_{CE} = 1 V	h_{FE}	>	40	
Transition frequency at f = 100 MHz I_C = 40 mA; V_{CE} = 10 V	f_T	>	490	MHz
Voltage gain at f = 36 MHz (see Fig. 4) I_C = 20 mA; V_{CE} ≈ 10,4 V	G_v	typ.	24	dB
Interference voltage for K = 1% (see Fig. 3)	$V_{(int)rms}$	typ.	120	mV

MECHANICAL DATA

Dimensions in mm

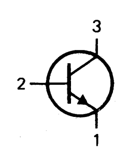
Fig. 1 SOT-23.



TOP VIEW

Marking code

B26



See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	V_{CBO}	max.	40	V
Collector-emitter voltage (open base)	V_{CEO}	max.	15	V
Emitter-base voltage (open collector)	V_{EBO}	max.	4,5	V
Collector current (d.c.)	I_C	max.	100	mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300	mW
Storage temperature	T_{stg}		−55 to +150	°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE

From junction to tab	$R_{th\ j\text{-}t}$	=	430	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current				
$I_E = 0$; $V_{CB} = 20$ V	I_{CBO}	<	400	nA
$I_E = 0$; $V_{CB} = 20$ V; $T_j = 125$ °C	I_{CBO}	<	30	μA
Emitter cut-off current				
$I_C = 0$; $V_{EB} = 2$ V	I_{EBO}	<	100	nA
D.C. current gain				
$I_C = 10$ mA; $V_{CE} = 1$ V	h_{FE}	>	40	
Transition frequency at f = 100 MHz				
$I_C = 10$ mA; $V_{CE} = 10$ V	f_T	>	500	MHz
$I_C = 40$ mA; $V_{CE} = 10$ V	f_T	>	490	MHz
Collector capacitance at f = 1 MHz				
$I_E = I_e = 0$; $V_{CB} = 10$ V	C_c	typ.	2,2	pF
		<	3,5	pF
Emitter capacitance at f = 1 MHz				
$I_C = I_c = 0$; $V_{EB} = 1$ V	C_e	<	4,5	pF
Feedback capacitance at f = 1 MHz				
$I_C = 0$; $V_{CE} = 10$ V	C_{re}	typ.	1,6	pF
		<	2,2	pF

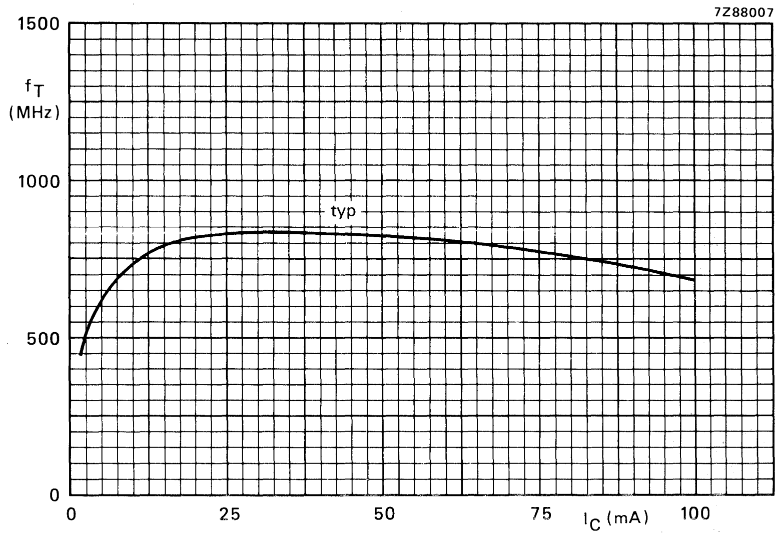
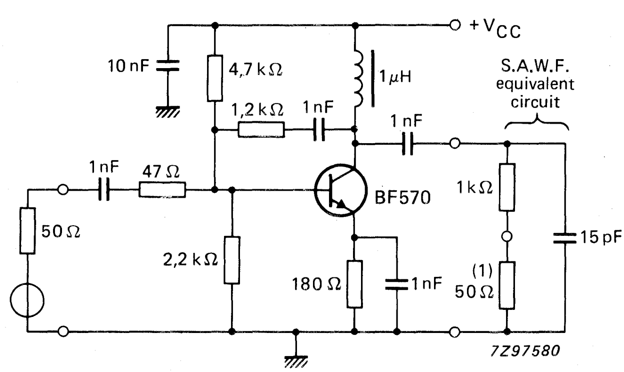


Fig. 2 V_{CE} = 10 V; T_j = 25 °C.

APPLICATION INFORMATION



(1) Test instrument load.

Fig. 3 Large-signal handling i.f. preamplifier for surface acoustic wave filter.

Performance

Supply voltage	V_{CC}	=	12 V
Collector current	I_C	=	20 mA
Measuring frequency	f_i	=	36 MHz
Input impedance	Z_i	typ.	50 Ω//1 pF
Output impedance	Z_o	<	100 Ω
Voltage gain G_v (in dB) = $20 \log \frac{V_o}{V_i}$	G_v	typ.	24 dB
Interference voltage for K = 1%*	$V_{(int)rms}$	typ.	120 mV

* Input terminal voltage at 50 Ω internal resistance of signal generator, interference frequency 40 MHz, 80% modulated with 1 kHz.

SILICON PLANAR TRANSISTOR

P-N-P transistor in a microminiature envelope primarily intended for u.h.f. applications in thick and thin-film circuits.

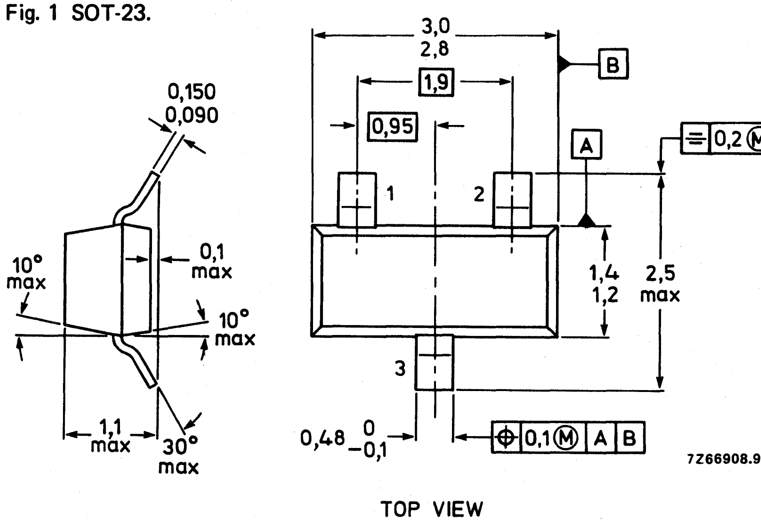
QUICK REFERENCE DATA

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	20	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	20	V
Collector current	$-I_C$	max.	25	mA
Total power dissipation up to T_{amb} = 85 °C	P_{tot}	max.	150	mW
Junction temperature	T_j	max.	150	°C
Transition frequency at f = 100 MHz I_E = 10 mA; $-V_{CB}$ = 10 V	f_T	typ.	1350	MHz
Transducer gain (common base) I_E = 10 mA; $-V_{CB}$ = 10 V; f = 800 MHz R_S = 60 Ω; R_L = 500 Ω; T_{amb} = 25 °C	G_{tr}	typ.	16	dB
Noise figure (common base) I_E = 10 mA; $-V_{CB}$ = 10 V; f = 800 MHz R_S = 60 Ω; R_L = 500 Ω	F	typ.	4,5	dB

MECHANICAL DATA

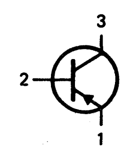
Dimensions in mm

Fig. 1 SOT-23.



Marking code

BF579 = G7



See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter) see Fig. 2	$-V_{CBO}$	max.	20 V
Collector-emitter voltage (open base) see Fig. 2	$-V_{CEO}$	max.	20 V
Emitter-base voltage (open collector) see Fig. 2	$-V_{EBO}$	max.	3 V
Collector current	$-I_C$	max.	25 mA
Base current (d.c.)	$-I_B$	max.	10 mA
Total power dissipation up to T_{amb} = 85 °C**	P_{tot}	max.	150 mW
Storage temperature	T_{stg}	−65 to + 150 °C	
Junction temperature	T_j	max.	150 °C

THERMAL CHARACTERISTICS*

$T_j = P \times (R_{th\,j\text{-}t} + R_{th\,t\text{-}s} + R_{th\,s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\,j\text{-}t}$	=	60 K/W
From tab to soldering points	$R_{th\,t\text{-}s}$	=	280 K/W
From soldering points to ambient**	$R_{th\,s\text{-}a}$	=	90 K/W

CHARACTERISTICS

T_{amb} = 25 °C

Collector cut-off current $I_E = 0$; $-V_{CB} = 15$ V	$-I_{CBO}$	<	100 nA
Emitter cut-off current $I_C = 0$; $-V_{EB} = 1$ V	$-I_{EBO}$	<	100 nA
D.C. current gain $I_C = 10$ mA; $-V_{CE} = 10$ V	h_{FE}	>	20
Transition frequency at f = 100 MHz $I_E = 10$ mA; $-V_{CB} = 10$ V	f_T	typ.	1350 MHz
Feedback capacitance at f = 500 kHz $I_E = 7$ mA; $-V_{CB} = 10$ V	C_{re}	typ.	0,46 pF
$I_E = 0$; $-V_{CB} = 10$ V	C_{rb}	typ.	160 fF
Transducer gain (common base) $I_E = 10$ mA; $-V_{CB} = 10$ V; f = 800 MHz $R_S = 60\ \Omega$; $R_L = 500\ \Omega$	G_{tr}	typ.	16 dB
Noise figure (common base) $I_E = 10$ mA; $-V_{CB} = 10$ V; f = 800 MHz $R_S = 60\ \Omega$; $R_L = 500\ \Omega$	F	typ.	4,5 dB

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

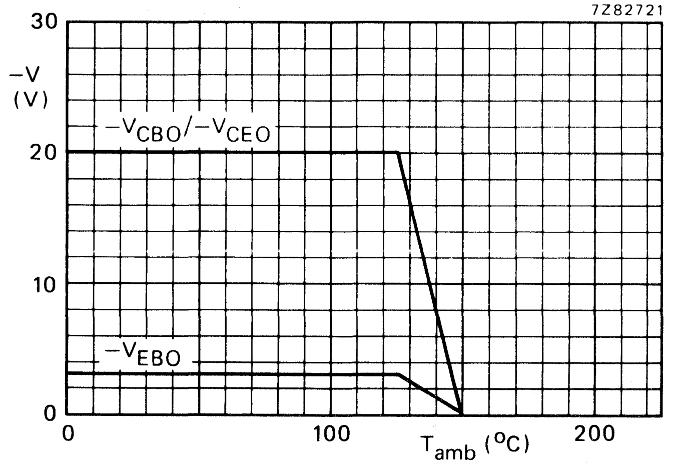


Fig. 2 Voltage derating curves.

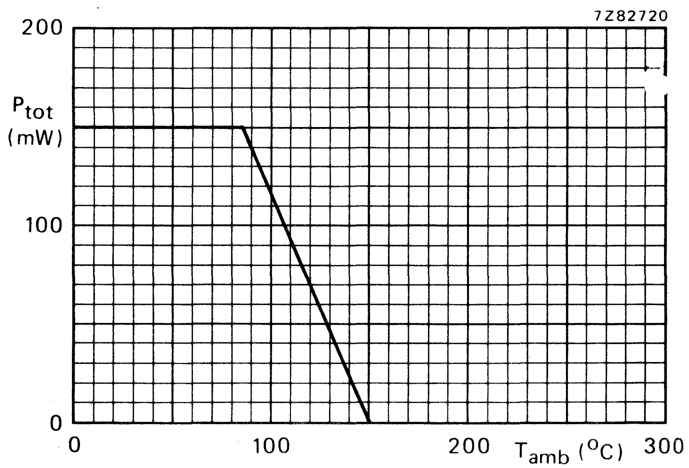


Fig. 3 Power derating curve.

SILICON EPITAXIAL TRANSISTORS

- **For video output stages**

N-P-N transistors in a microminiature plastic envelope intended for class-B video output stages in colour television receivers.

P-N-P complements are BF621 and BF623 respectively.

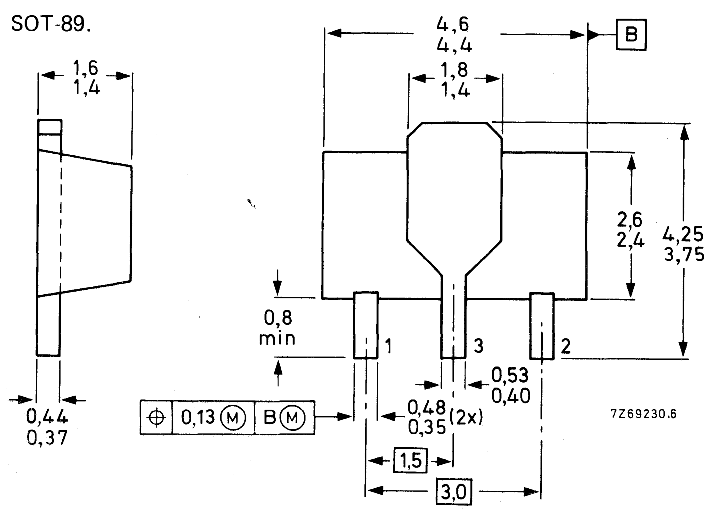
QUICK REFERENCE DATA

			BF620	BF622	
Collector-base voltage (open emitter)	V_{CBO}	max.	300	250	V
Collector-emitter voltage (open base)	V_{CEO}	max.	–	250	V
Collector-emitter voltage (R_{BE} = 2,7 kΩ)	V_{CER}	max.	300	–	V
Collector current (peak value)	I_{CM}	max.	100		mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	1		W
Junction temperature	T_j	max.	150		°C
D.C. current gain I_C = 25 mA; V_{CE} = 20 V	h_{FE}	>	50		
Transition frequency at f = 35 MHz I_C = 10 mA; V_{CE} = 10 V	f_T	>	60		MHz
Feedback capacitance at f = 1 MHz I_C = 0; V_{CE} = 30 V	C_{re}	<	1,6		pF

MECHANICAL DATA

Fig. 1 SOT-89.

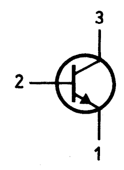
Dimensions in mm



BOTTOM VIEW

Mark

BF620 = DC
BF622 = DA



See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BF620	BF622	
Collector-base voltage (open emitter)	V_{CBO}	max.	300	250	V
Collector-emitter voltage (open base)	V_{CEO}	max.	–	250	V
Collector-emitter voltage (R_{BE} = 2,7 kΩ)	V_{CER}	max.	300	–	V
Emitter-base voltage (open collector)	V_{EBO}	max.	5		V
Collector current (d.c.)	I_C	max.	50		mA
Collector current (peak value)	I_{CM}	max.	100		mA
Total power dissipation up to T_{amb} = 25 °C mounted on a ceramic substrate area = 2,5 cm²; thickness = 0,7 mm	P_{tot}	max.	1		W
Storage temperature	T_{stg}		–65 to + 150		°C
Junction temperature	T_j	max.	150		°C

THERMAL RESISTANCE*

From junction to collector tab	$R_{th\ j\text{-}tab}$	=	25	K/W
From junction to ambient in free air mounted on a ceramic substrate area = 2,5 cm²; thickness = 0,7 mm	$R_{th\ j\text{-}a}$	=	125	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BF620	BF622	
Collector cut-off current $I_E = 0$; V_{CB} = 200 V	I_{CBO}	<	10	10	nA
Collector-emitter voltage R_{BE} = 2,7 kΩ; V_{CE} = 250 V	I_{CER}	<	50	–	nA
R_{BE} = 2,7 kΩ; V_{CE} = 200 V; T_j = 150 °C	I_{CER}	<	10	10	μA
Saturation voltage I_C = 30 mA; I_B = 5 mA	$V_{CE\ sat}$	<	0,6		V
D.C. current gain I_C = 25 mA; V_{CE} = 20 V	h_{FE}	>	50		
Transition frequency at f = 35 MHz I_C = 10 mA; V_{CE} = 10 V	f_T	>	60		MHz
Feedback capacitance at f = 1 MHz $I_C = 0$; V_{CE} = 30 V	C_{re}	<	1,6		pF

* See *Thermal characteristics.*

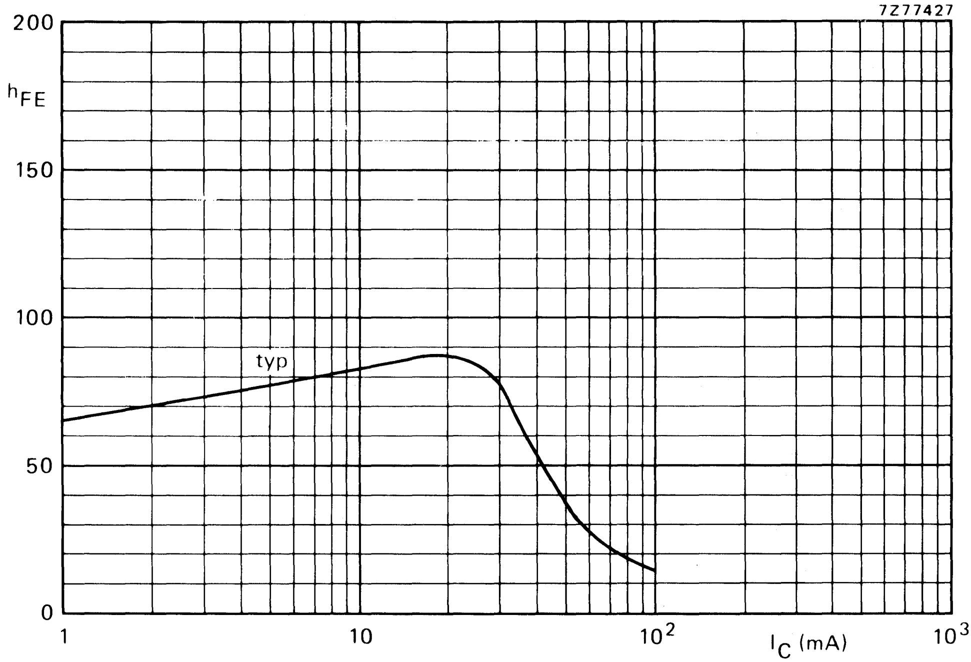


Fig. 2 Typical values at V_{CE} = 20 V; T_j = 25 °C.

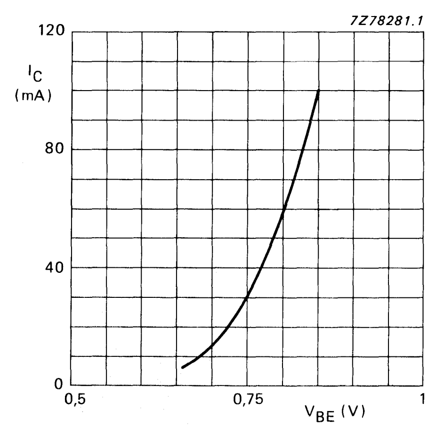


Fig. 3 V_{CE} = 20 V; T_j = 25 °C.

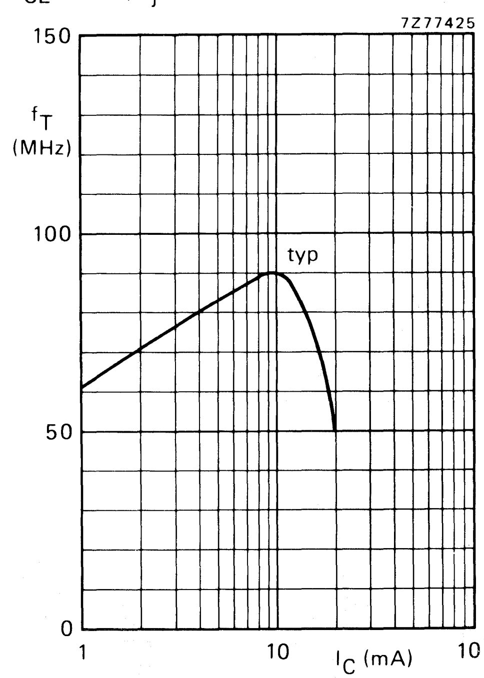


Fig. 4 V_{CE} = 10 V; T_j = 25 °C; f = 35 MHz.

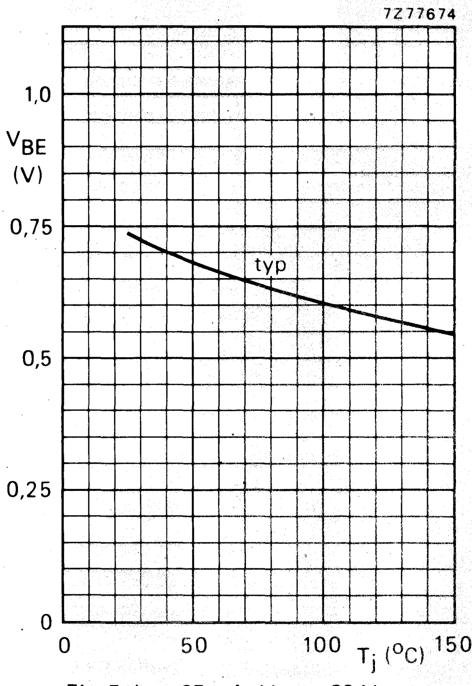


Fig. 5 I_C = 25 mA; V_{CE} = 20 V.

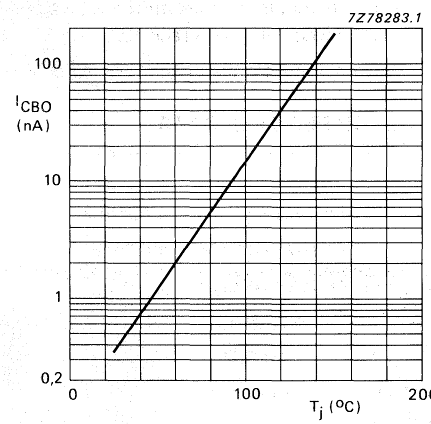


Fig. 6 V_{CB} = 200 V; typical values.

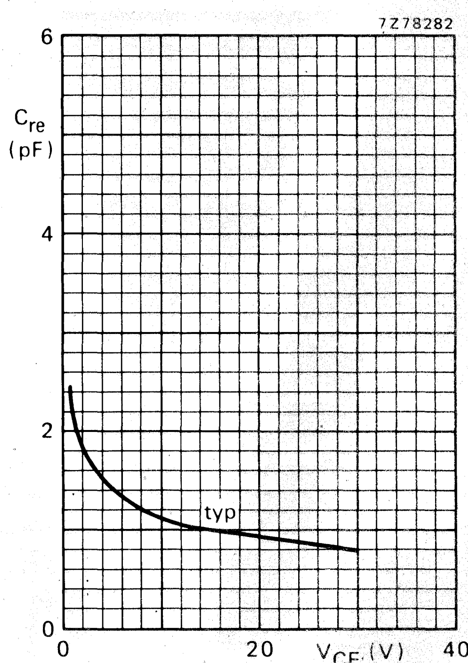


Fig. 7 I_C = 0; f = 1 MHz; T_j = 25 °C.

SILICON EPITAXIAL TRANSISTORS

- **For video output stages**

P-N-P transistors in a microminiature plastic envelope intended for application in class-B video output stages in colour television receivers.

N-P-N complements are BF620 and BF622 respectively.

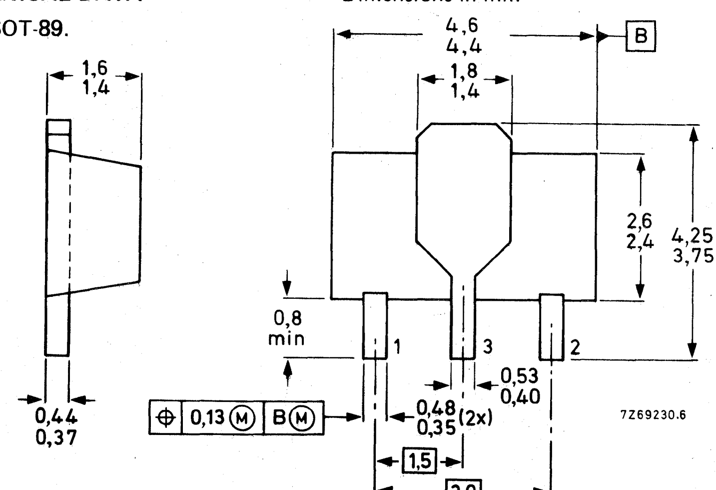
QUICK REFERENCE DATA

			BF621	BF623	
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	300	250	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	–	250	V
Collector-emitter voltage (R_{BE} = 2,7 kΩ)	$-V_{CER}$	max.	300	–	V
Collector current (peak value)	$-I_{CM}$	max.	100		mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	1		W
Junction temperature	T_j	max.	150		°C
D.C. current gain $-I_C$ = 25 mA; $-V_{CE}$ = 20 V	h_{FE}	>	50		
Transition frequency at f = 35 MHz $-I_C$ = 10 mA; $-V_{CE}$ = 10 V	f_T	>	60		MHz
Feedback capacitance at f = 1 MHz I_C = 0; $-V_{CE}$ = 30 V	C_{re}	<	1,6		pF

MECHANICAL DATA

Dimensions in mm

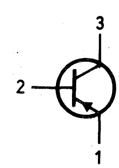
Fig. 1 SOT-89.



BOTTOM VIEW

Mark

BF621 = DF
BF623 = DB



See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BF621	BF623	
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	300	250	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	–	250	V
Collector-emitter voltage (R_{BE} = 2,7 kΩ)	$-V_{CER}$	max.	300	–	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5		V
Collector current (d.c.)	$-I_C$	max.	50		mA
Collector current (peak value)	$-I_{CM}$	max.	100		mA
Total power dissipation up to T_{amb} = 25 °C mounted on a ceramic substrate area = 2,5 cm²; thickness = 0,7 mm	P_{tot}	max.	1		W
Storage temperature	T_{stg}		–65 to +150		°C
Junction temperature	T_j	max.	150		°C

THERMAL RESISTANCE*

From junction to collector tab	$R_{th\ j\text{-}tab}$	=	25	K/W
From junction to ambient in free air mounted on a ceramic substrate area = 2,5 cm²; thickness = 0,7 mm	$R_{th\ j\text{-}a}$	=	125	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BF621	BF623	
Collector cut-off current $I_E = 0$; $-V_{CB}$ = 200 V	$-I_{CBO}$	<	10	10	nA
Collector-emitter voltage R_{BE} = 2,7 kΩ; $-V_{CE}$ = 250 V	$-I_{CER}$	<	50	–	nA
R_{BE} = 2,7 kΩ; $-V_{CE}$ = 200 V; T_j = 150 °C	$-I_{CER}$	<	10	10	μA
Saturation voltage $-I_C$ = 30 mA; $-I_B$ = 5 mA	$-V_{CEsat}$	<	0,8		V
D.C. current gain $-I_C$ = 25 mA; $-V_{CE}$ = 20 V	h_{FE}	>	50		
Transition frequency at f = 35 MHz $-I_C$ = 10 mA; $-V_{CE}$ = 10 V	f_T	>	60		MHz
Feedback capacitance at f = 1 MHz $I_C = 0$; $-V_{CE}$ = 30 V	C_{re}	<	1,6		pF

* See *Thermal characteristics.*

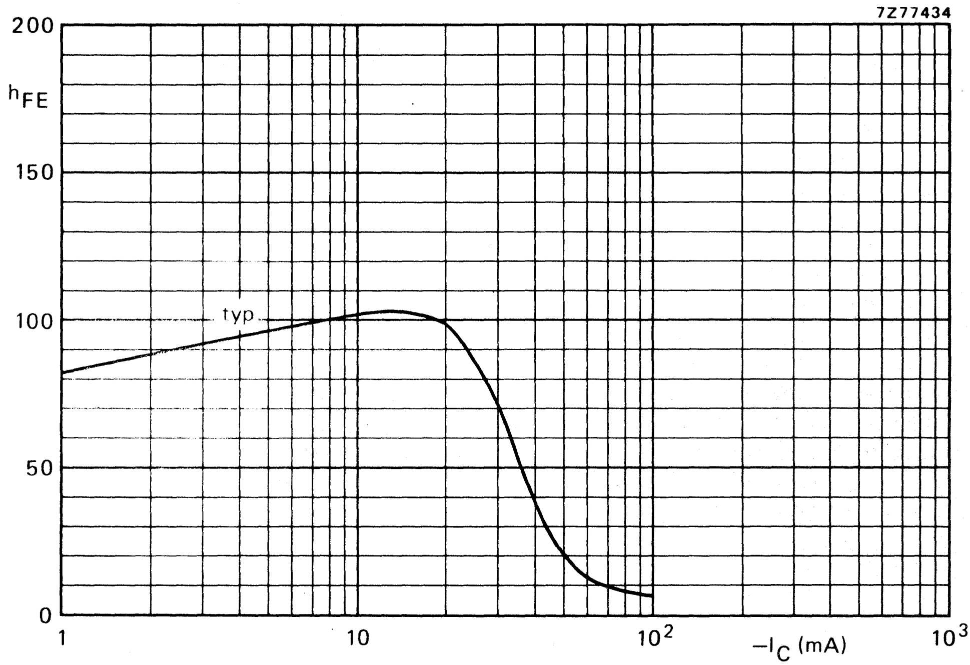


Fig. 2 Typical values at $-V_{CE}$ = 20 V; T_j = 25 °C.

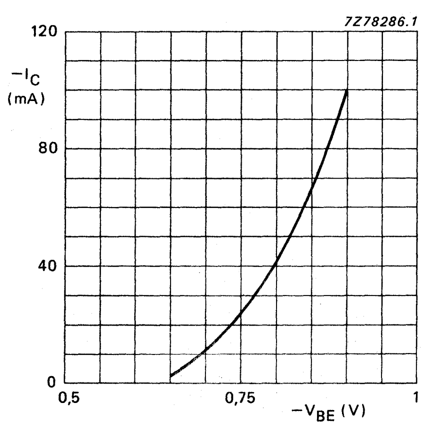


Fig. 3 $-V_{CE}$ = 20 V; T_j = 25 °C; typical values.

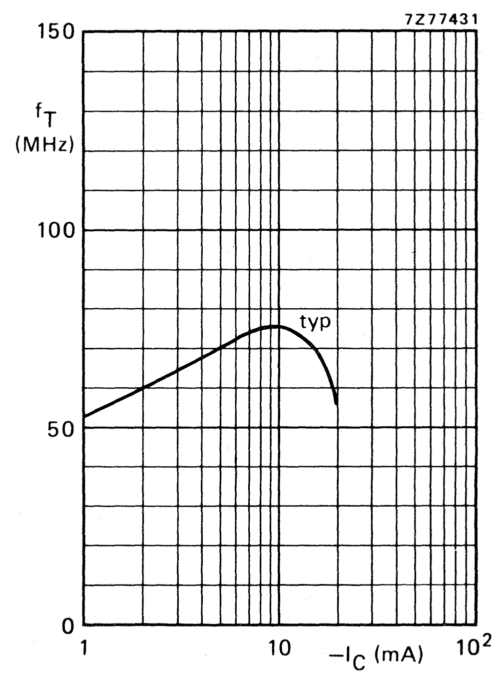


Fig. 4 $-V_{CE}$ = 10 V; T_j = 25 °C; f = 35 MHz.

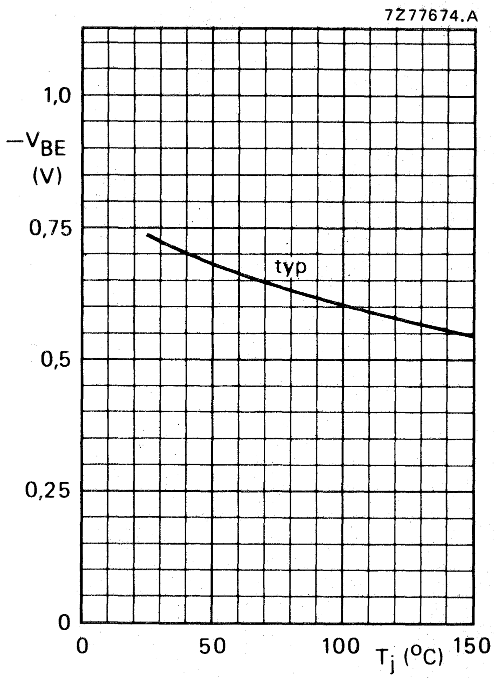


Fig. 5 $-I_C$ = 25 mA; $-V_{CE}$ = 20 V.

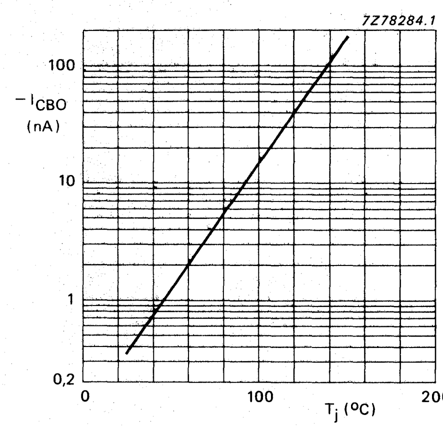


Fig. 6 $-V_{CB}$ = 200 V ; typical values.

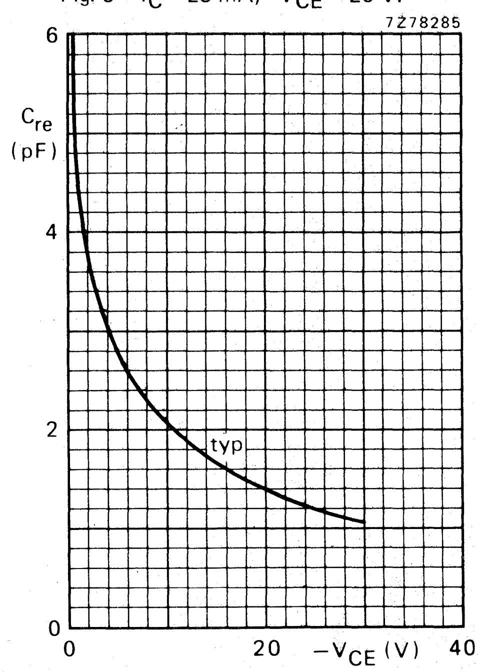


Fig. 7 I_C = 0; f = 1 MHz; T_j = 25 °C.

SILICON PLANAR TRANSISTOR

P-N-P transistor, in a microminiature plastic envelope; intended for use as oscillator in v.h.f. tuners with extended frequency range and/or in conjunction with MOS-FETs in thick and thin-film circuits.

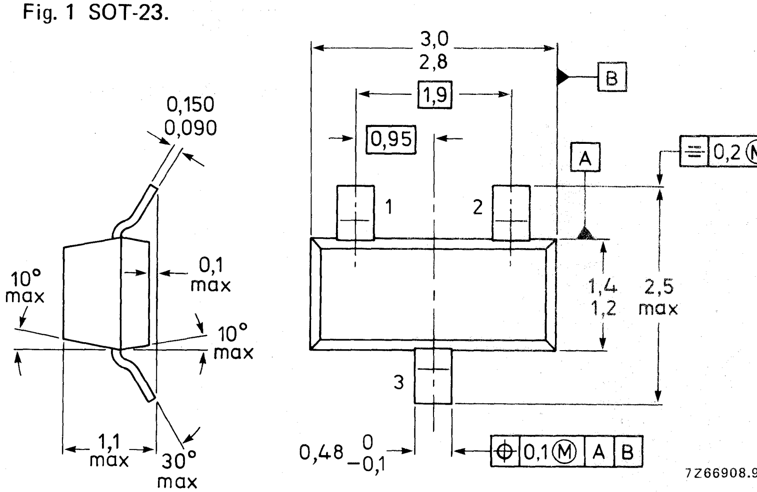
QUICK REFERENCE DATA

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	40	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	30	V
Collector current (peak value)	$-I_{CM}$	max.	25	mA
Total power dissipation up to T_{amb} = 60 °C	P_{tot}	max.	200	mW
Junction temperature	T_j	max.	150	°C
Transition frequency at f = 100 MHz I_E = 5 mA; $-V_{CB}$ = 10 V	f_T	typ.	650	MHz

MECHANICAL DATA

Dimensions in mm

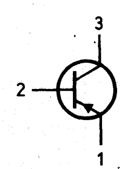
Fig. 1 SOT-23.



TOP VIEW

Marking code

BF660 = G8



See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	40	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	30	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	4	V
Collector current (peak value)	$-I_{CM}$	max.	25	mA
Base current (d.c.)	$-I_B$	max.	10	mA
Total power dissipation up to T_{amb} = 60 °C **	P_{tot}	max.	200	mW
Storage temperature	T_{stg}		−65 to + 150	°C
Junction temperature	T_j	max.	150	°C

THERMAL CHARACTERISTICS*

$T_j = P \times (R_{th\,j\text{-}t} + R_{th\,t\text{-}s} + R_{th\,s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\,j\text{-}t}$	=	60	K/W
From tab to soldering points	$R_{th\,t\text{-}s}$	=	280	K/W
From soldering points to ambient**	$R_{th\,s\text{-}a}$	=	90	K/W

CHARACTERISTICS

T_{amb} = 25 °C

Collector cut-off current $I_E = 0$; $-V_{CB} = 20$ V	$-I_{CBO}$	<	50	nA
D.C. current gain $I_E = 3$ mA; $-V_{CE} = 10$ V	h_{FE}	>	30	
Transition frequency at f = 100 MHz $I_E = 5$ mA; $-V_{CB} = 10$ V	f_T	typ.	650	MHz
Feedback capacitance at f = 1 MHz $I_E = 1$ mA; $-V_{CB} = 10$ V	C_{re}	typ.	0,65	pF

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

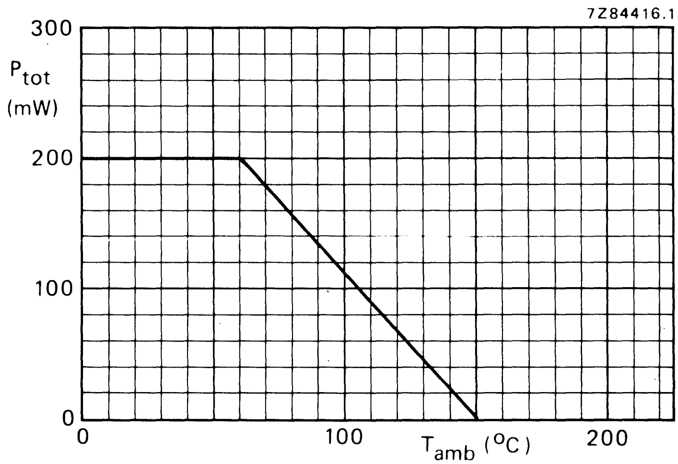


Fig. 2 Power derating curve.

SILICON PLANAR TRANSISTOR

P-N-P transistor in a microminiature plastic envelope, primarily intended for application as gain controlled amplifier e.g. in v.h.f. and u.h.f. television tuners in thick and thin-film circuits.

QUICK REFERENCE DATA

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	30	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	30	V
Collector current (d.c.)	$-I_C$	max.	20	mA
Total power dissipation up to T_{amb} = 60 °C	P_{tot}	max.	200	mW
Junction temperature	T_j	max.	150	°C
Transition frequency at f = 100 MHz I_E = 3 mA; $-V_{CB}$ = 10 V	f_T	typ.	900	MHz
Transducer gain (common base) I_E = 3 mA; $-V_{CB}$ = 10 V; f = 800 MHz R_S = 60 Ω; R_L = 500 Ω	G_{tr}	typ.	13	dB
Noise figure (common base) I_E = 3 mA; $-V_{CB}$ = 10 V; f = 800 MHz R_S = 60 Ω; R_L = 500 Ω	F	typ.	4	dB

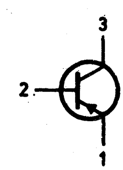
MECHANICAL DATA

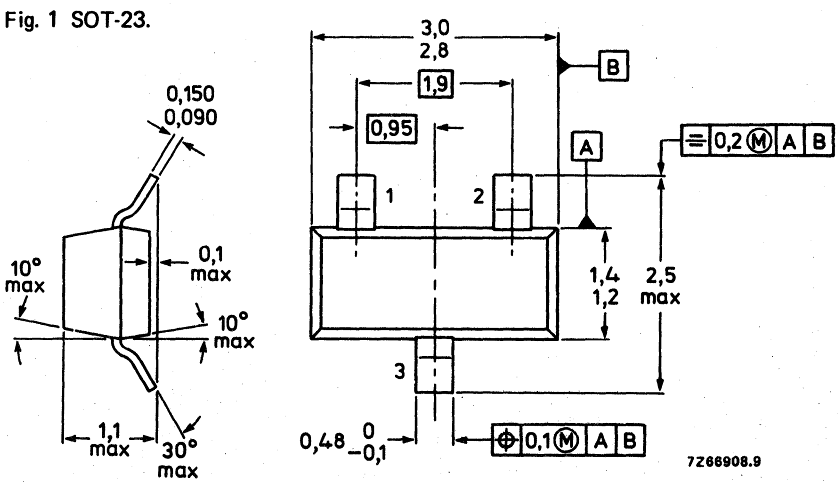
Dimensions in mm

Fig. 1 SOT-23.

Marking code

BF767 = G9





TOP VIEW

See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	30 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	30 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	3 V
Collector current (d.c.)	$-I_C$	max.	20 mA
Total power dissipation up to T_{amb} = 60 °C **	P_{tot}	max.	200 mW
Storage temperature	T_{stg}	−65 to + 150 °C	
Junction temperature	T_j	max.	150 °C

THERMAL CHARACTERISTICS*

$T_j = P \times (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	60 K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280 K/W
From soldering points to ambient**	$R_{th\ s\text{-}a}$	=	90 K/W

CHARACTERISTICS

T_{amb} = 25 °C; unless otherwise specified

Collector cut-off current			
$I_E = 0$; $-V_{CB} = 15$ V	$-I_{CBO}$	<	100 nA
D.C. current gain			
$-I_E = 3$ mA; $-V_{CB} = 10$ V	h_{FE}	>	15
		typ.	60
$-I_E = 7$ mA; $-V_{CB} = 4$ V	h_{FE}	>	10
Transition frequency at f = 100 MHz			
$I_E = 3$ mA; $-V_{CB} = 10$ V	f_T	typ.	900 MHz
$I_E = 7$ mA; $-V_{CB} = 5$ V	f_T	typ.	90 MHz
Feedback capacitance at f = 500 kHz			
$I_E = 1$ mA; $-V_{CB} = 10$ V	C_{re}	typ.	0,3 pF
$I_E = 0$; $-V_{CB} = 10$ V	C_{rb}	typ.	160 fF
Transducer gain (common base)			
$I_E = 3$ mA; $-V_{CB} = 10$ V; f = 800 MHz $R_S = 60\ \Omega$; $R_L = 500\ \Omega$	G_{tr}	typ.	13 dB
Noise figure (common base)			
$I_E = 3$ mA; $-V_{CB} = 10$ V; f = 800 MHz $R_S = 60\ \Omega$; $R_L = 500\ \Omega$	F	typ.	4 dB

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

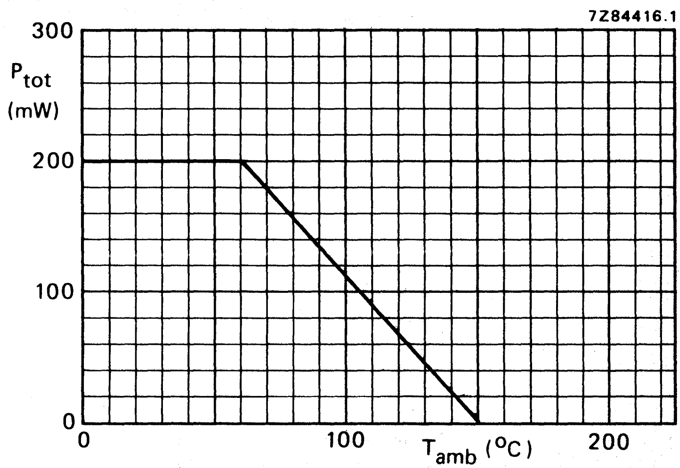


Fig. 2 Power derating curve.

SILICON EPITAXIAL TRANSISTORS

N-P-N transistors in a microminiature plastic envelope intended for application in thick and thin-film circuits. Primarily intended for use in telephony and professional communication equipment. P-N-P components are BF821, BF823 respectively.

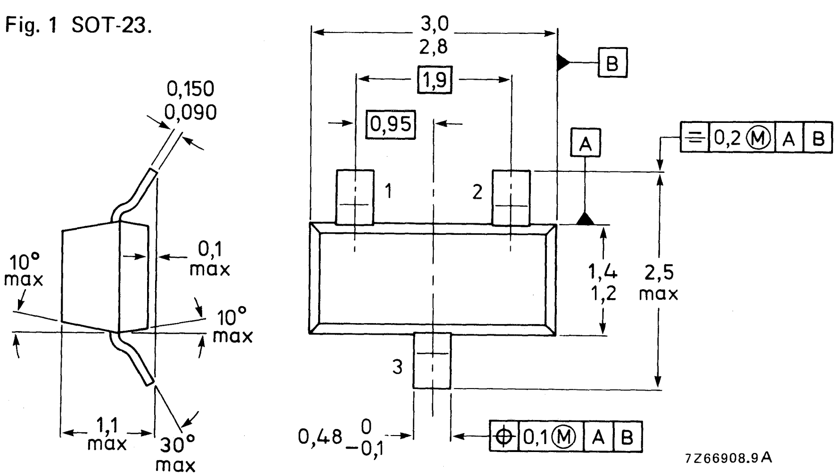
QUICK REFERENCE DATA

			BF820	BF822	
Collector-base voltage (open emitter)	V_{CBO}	max.	300	250	V
Collector-emitter voltage (open base)	V_{CEO}	max.	–	250	V
Collector-emitter voltage (R_{BE} = 2,7 kΩ)	V_{CER}	max.	300	–	V
Collector current (peak value)	I_{CM}	max.	100		mA
Total power dissipation up to T_{amb} = 35 °C	P_{tot}	max.	310		mW
Junction temperature	T_j	max.	150		°C
D.C. current gain I_C = 25 mA; V_{CE} = 20 V	h_{FE}	>	50		
Feedback capacitance at f = 1 MHz I_C = 0; V_{CE} = 30 V	C_{re}	<	1,6		pF
Transition frequency at f = 35 MHz I_C = 10 mA; V_{CE} = 10 V	f_T	>	60		MHz

MECHANICAL DATA

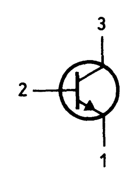
Dimensions in mm

Fig. 1 SOT-23.



TOP VIEW

Mark
BF820 = 1 V
BF822 = 1 X



See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BF820	BF822	
Collector-base voltage (open emitter)	V_{CBO}	max.	300	250	V
Collector-emitter voltage (open base)	V_{CEO}	max.	–	250	V
Collector-emitter voltage (R_{BE} = 2,7 kΩ)	V_{CER}	max.	300	–	V
Emitter-base voltage (open collector)	V_{EBO}	max.	5		V
Collector current (d.c.)	I_C	max.	50		mA
Collector current (peak value)	I_{CM}	max.	100		mA
Total power dissipation* up to T_{amb} = 35 °C	P_{tot}	max.	310		mW
Storage temperature	T_{stg}		–65 to +150		°C
Junction temperature	T_j	max.	150		°C

THERMAL CHARACTERISTICS**

$T_j = P(R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

from junction to tab	$R_{th\ j\text{-}t}$	=	50	K/W
from tab to soldering points	$R_{th\ t\text{-}s}$	=	260	K/W
from soldering points to ambient*	$R_{th\ s\text{-}a}$	=	60	K/W

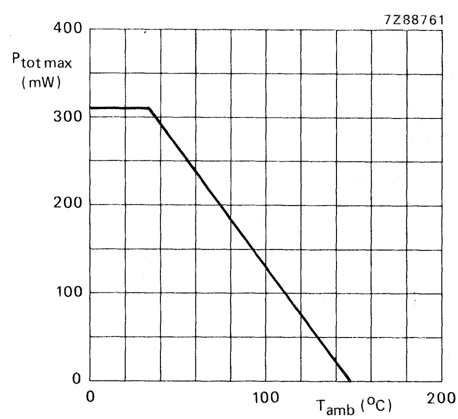


Fig. 2 Power derating curve.

* Mounted on a ceramic substrate: area = 2,5 cm^2; thickness = 0,7 mm.
** See *Thermal characteristics.*

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BF820	BF822	
Collector cut-off current					
I_E = 0; V_{CB} = 200 V	I_{CBO}	<	10	10	nA
Collector-emitter voltage					
R_{BE} = 2,7 kΩ; V_{CE} = 250 V	I_{CER}	<	50	50	nA
R_{BE} = 2,7 kΩ; V_{CE} = 200 V; T_j = 150 °C	I_{CER}	<	10	10	μA
Saturation voltage					
I_C = 30 mA; I_B = 5 mA	$V_{CE\,sat}$	<	0,6		V
D.C. current gain					
I_C = 25 mA; V_{CE} = 20 V	h_{FE}	>	50		
Transition frequency at f = 35 MHz					
I_C = 10 mA; V_{CE} = 10 V	f_T	>	60		MHz
Feedback capacitance at f = 1 MHz					
I_C = 0; V_{CE} = 30 V	C_{re}	<	1,6		pF

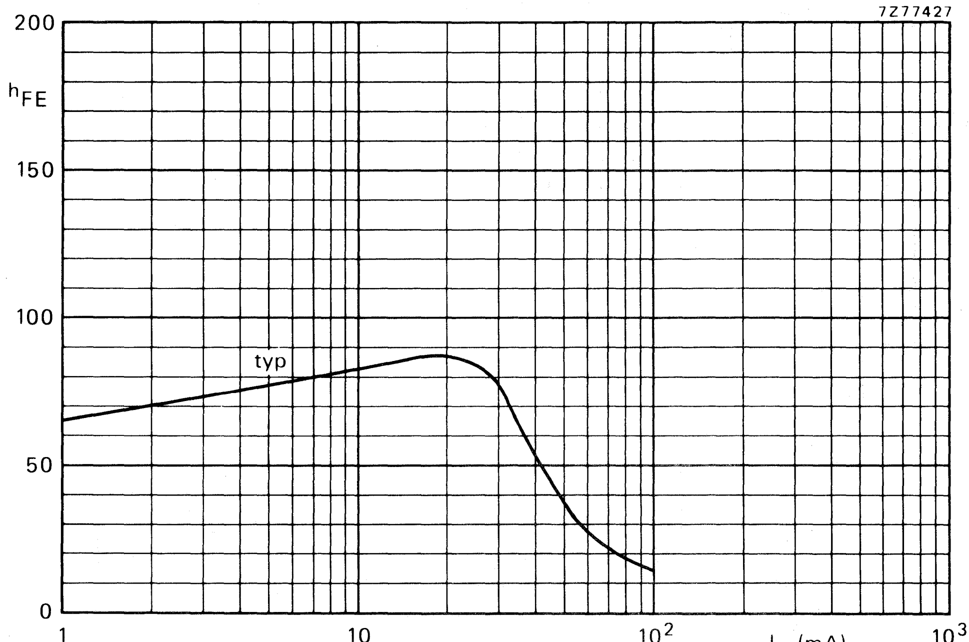


Fig. 3 V_{CE} = 20 V; T_j = 25 °C.

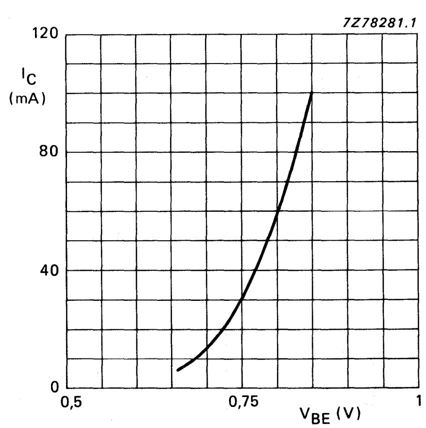


Fig. 4 V_{CE} = 20 V; T_j = 25 °C; typical values.

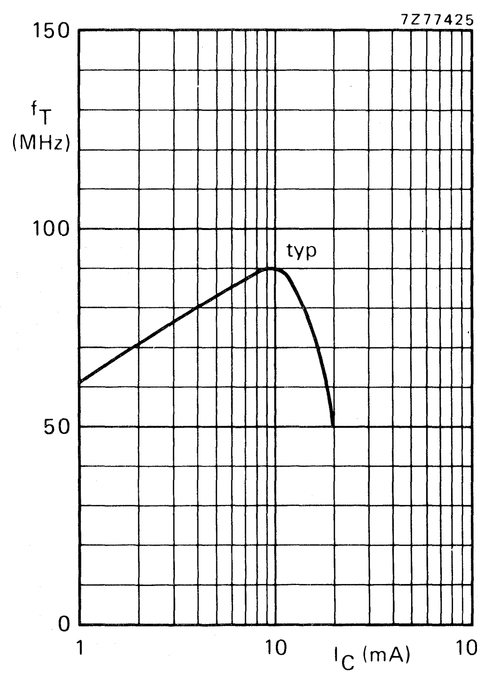


Fig. 5 V_{CE} = 10 V; T_j = 25 °C, f = 35 MHz.

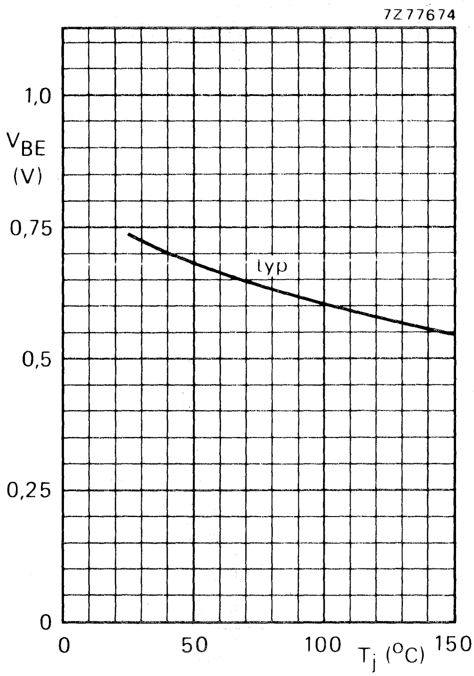


Fig. 6 I_C = 25 mA; V_{CE} = 20 V.

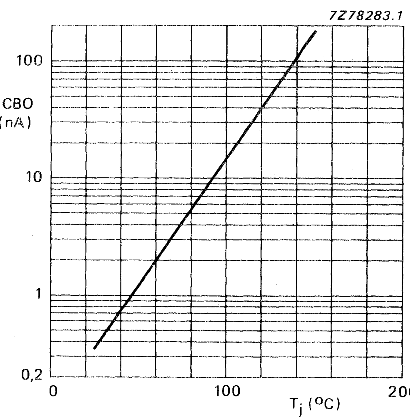


Fig. 7 V_{CB} = 200 V; typical values.

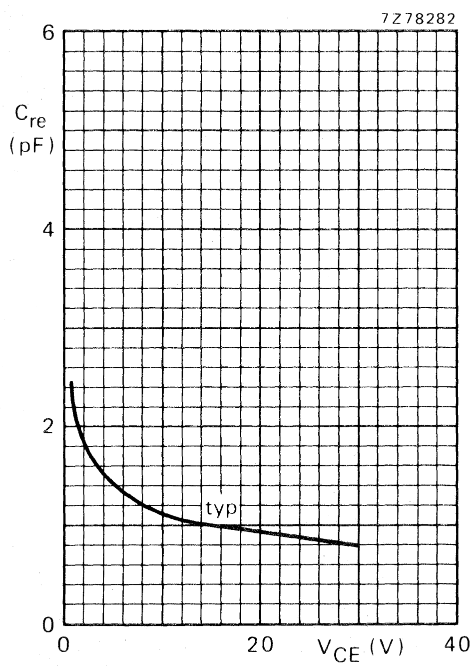


Fig. 8 I_C = 0; f = 1 MHz; T_j = 25 °C.

SILICON EPITAXIAL TRANSISTORS

P-N-P transistors in a microminiature plastic envelope intended for application in thick and thin-film circuits. Primarily intended for use in telephony and professional communication equipment. N-P-N complements are BF820, BF822 respectively.

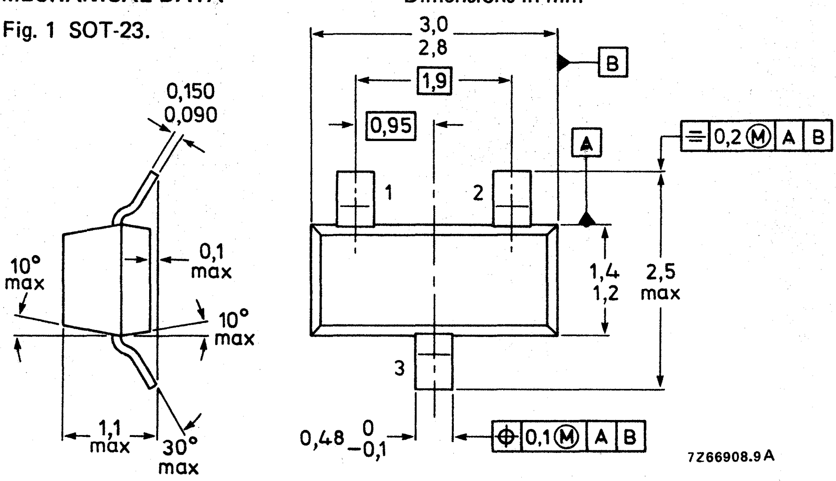
QUICK REFERENCE DATA

			BF821	BF823	
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	300	250	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	–	250	V
Collector-emitter voltage (R_{BE} = 2,7 kΩ)	$-V_{CER}$	max.	300	–	V
Collector current (peak value)	$-I_{CM}$	max.	100		mA
Total power dissipation up to T_{amb} = 35 °C	P_{tot}	max.	310		mW
Junction temperature	T_j	max.	150		°C
D.C. current gain $-I_C$ = 25 mA; $-V_{CE}$ = 20 V	h_{FE}	>	50		
Feedback capacitance at f = 1 MHz $-I_C$ = 0; $-V_{CE}$ = 30 V	C_{re}	<	1,6		pF
Transition frequency at f = 35 MHz $-I_C$ = 10 mA; $-V_{CE}$ = 10 V	f_T	>	60		MHz

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-23.

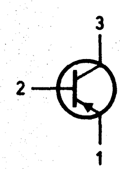


TOP VIEW

Mark

BF821 = 1W

BF823 = 1Y



See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BF821	BF823	
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	300	250	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	–	250	V
Collector-emitter voltage (R_{BE} = 2,7 kΩ)	$-V_{CER}$	max.	300	–	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5		V
Collector current (d.c.)	$-I_C$	max.	50		mA
Collector current (peak value)	$-I_{CM}$	max.	100		mA
Total power dissipation* up to T_{amb} = 35 °C	P_{tot}	max.	310		mW
Storage temperature	T_{stg}		–65 to +150		°C
Junction temperature	T_j	max.	150		°C

THERMAL CHARACTERISTICS**

$T_j = P(R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance				
from junction to tab	$R_{th\ j\text{-}t}$	=	50	K/W
from tab to soldering points	$R_{th\ t\text{-}s}$	=	260	K/W
from soldering points to ambient*	$R_{th\ s\text{-}a}$	=	60	K/W

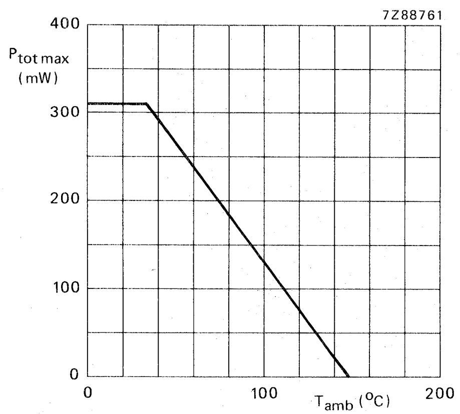


Fig. 2 Power derating curve.

* Mounted on a ceramic substrate: area = 2,5 cm^2; thickness = 0,7 mm.
** See *Thermal characteristics.*

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BF821	BF823	
Collector cut-off current					
$I_E = 0$; $-V_{CB} = 200$ V	$-I_{CBO}$	<	10	10	nA
Collector-emitter voltage					
$R_{BE} = 2{,}7$ kΩ; $-V_{CE} = 250$ V	$-I_{CER}$	<	50	50	nA
$R_{BE} = 2{,}7$ kΩ; $-V_{CE} = 200$ V; $T_j = 150$ °C	$-I_{CER}$	<	10	10	μA
Saturation voltage					
$-I_C = 30$ mA; $-I_B = 5$ mA	$-V_{CEsat}$	<	0,8		V
D.C. current gain					
$-I_C = 25$ mA; $-V_{CE} = 20$ V	h_{FE}	>	50		
Transition frequency at f = 35 MHz					
$-I_C = 10$ mA; $-V_{CE} = 10$ V	f_T	>	60		MHz
Feedback capacitance at f = 1 MHz					
$I_C = 0$; $-V_{CE} = 30$ V	C_{re}	<	1,6		pF

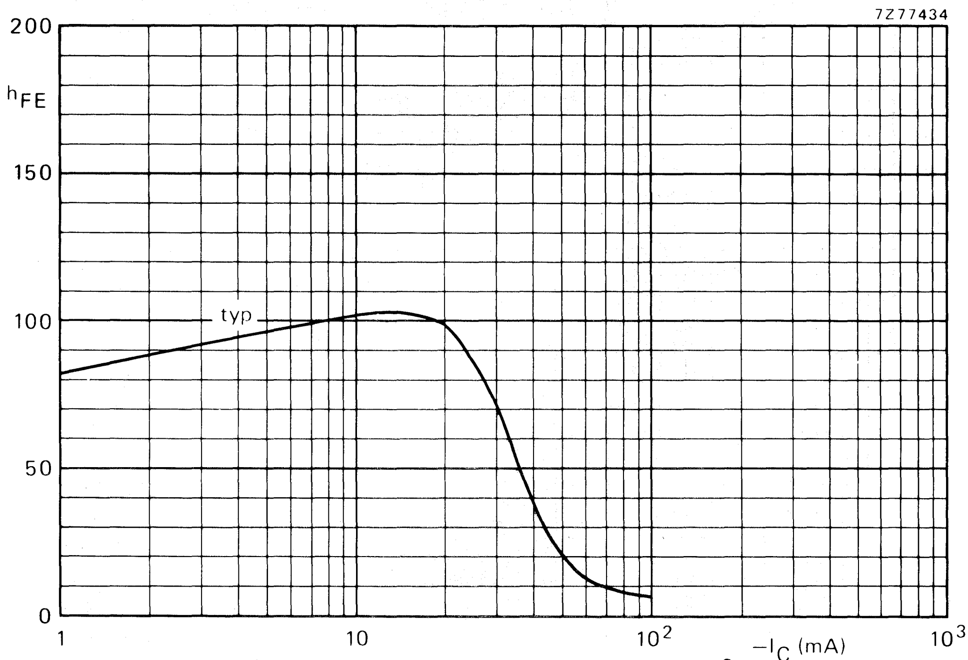


Fig. 3 D.C. current gain. $-V_{CE}$ = 20 V; T_j = 25 °C.

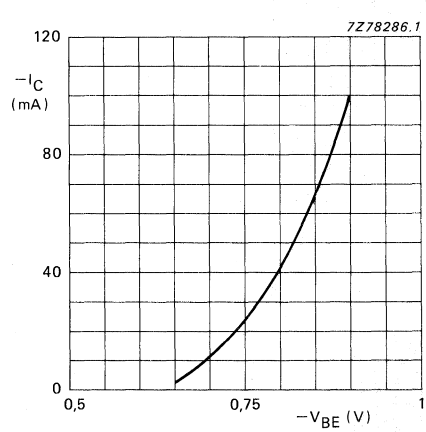


Fig. 4 $-V_{CE}$ = 20 V; T_j = 25 °C; typical values.

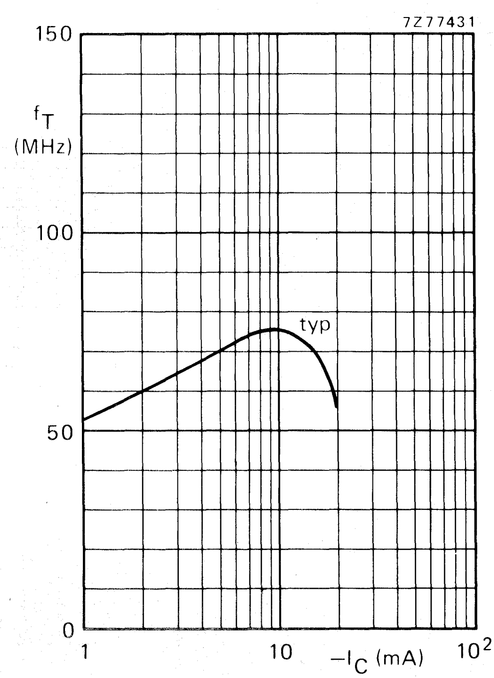


Fig. 5 $-V_{CE}$ = 10 V; T_j = 25 °C; f = 35 MHz.

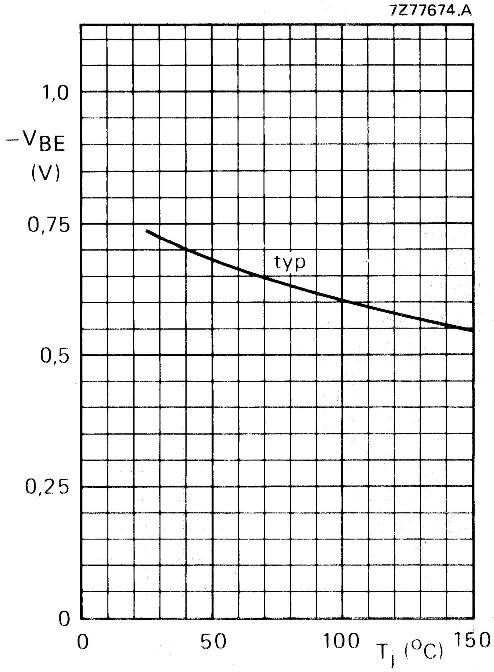


Fig. 6 $-I_C$ = 25 mA; $-V_{CE}$ = 20 V.

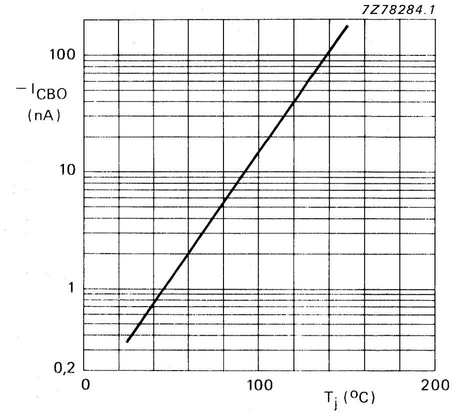


Fig. 7 $-V_{CB}$ = 200 V; typical values.

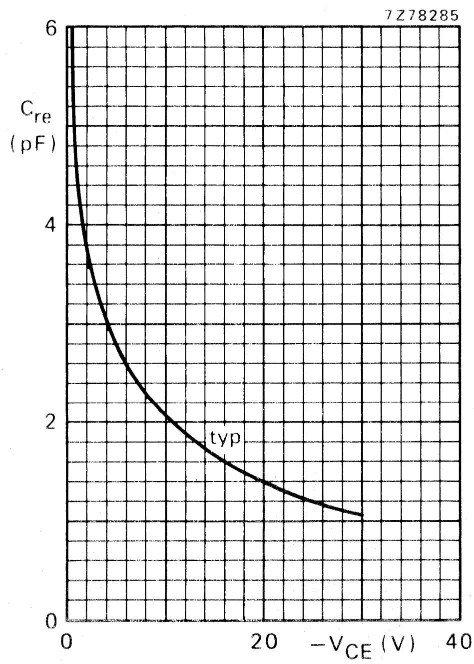


Fig. 8 I_C = 0; f = 1 MHz; T_j = 25 °C.

H.F. SILICON PLANAR EPITAXIAL TRANSISTOR

P-N-P transistor in a plastic SOT-23 envelope especially intended for r.f. stages in f.m. front-ends in common base configuration for SMD applications.

QUICK REFERENCE DATA

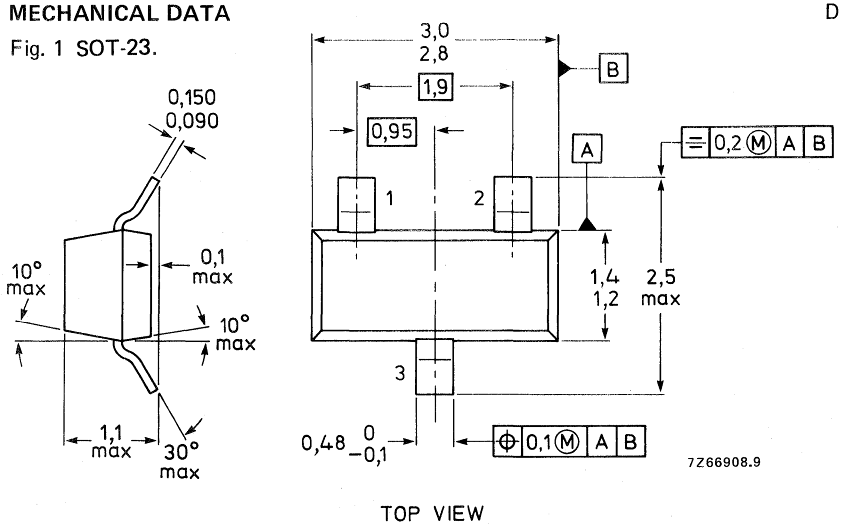
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	30	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	30	V
Collector current (d.c.)	$-I_C$	max.	25	mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300	mW
Junction temperature	T_j	max.	150	°C
Base current $-I_C$ = 4 mA; $-V_{CE}$ = 10 V	$-I_B$	typ. <	80 160	μA μA
Transition frequency $-I_C$ = 4 mA; $-V_{CE}$ = 10 V	f_T	typ.	450	MHz
Noise figure at f = 100 MHz $-I_C$ = 2 mA; $-V_{CE}$ = 10 V; G_s = 16,7 mS	F	typ.	3	dB
Feedback capacitance at f = 1 MHz V_{EB} = 0; $-V_{CB}$ = 10 V	C_{rb}	typ.	0,1	pF

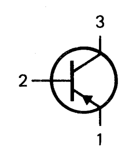
MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-23.

Marking: F8





RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	30	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	30	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	4	V
Collector current (d.c.)	$-I_C$	max.	25	mA
Total power dissipation up to T_{amb} = 25 °C *	P_{tot}	max.	300	mW
Storage temperature	T_{stg}	−55 to + 150		°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE

From junction to ambient in free air*	$R_{th\ j\text{-}a}$	=	430	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current				
$I_E = 0$; $-V_{CB} = 30$ V	$-I_{CBO}$	<	50	nA
Emitter cut-off current				
$I_C = 0$; $-V_{EB} = 4$ V	$-I_{EBO}$	<	10	μA
Base current				
$-I_C = 4$ mA; $-V_{CE} = 10$ V	$-I_B$	typ.	80	μA
		<	160	μA
$-I_C = 1$ mA; $-V_{CE} = 10$ V	$-I_B$	typ.	22	μA
Base-emitter voltage				
$-I_C = 4$ mA; $-V_{CE} = 10$ V	$-V_{BE}$	typ.	0,76	V
Transition frequency at f = 100 MHz				
$-I_C = 1$ mA; $-V_{CE} = 10$ V	f_T	typ.	350	MHz
$-I_C = 4$ mA; $-V_{CE} = 10$ V	f_T	typ.	450	MHz
$-I_C = 8$ mA; $-V_{CE} = 10$ V	f_T	typ.	440	MHz
Feedback capacitance at f = 1 MHz				
$V_{EB} = 0$; $-V_{CB} = 10$ V	C_{rb}	typ.	0,1	pF
Noise factor at f = 100 MHz				
$-I_C = 2$ mA; $-V_{CE} = 10$ V; $G_s = 16{,}7$ mS	F	typ.	3	dB
$-I_C = 5$ mA; $-V_{CE} = 10$ V; $G_s = 6{,}7$ mS; $-jB_s = 5$ mS	F	typ.	3,5	dB

* Mounted on ceramic substrate of 8 mm x 10 mm x 0,7 mm.

y-parameters (common base) at f = 100 MHz
$-I_C$ = 4 mA; $-V_{CB}$ = 10 V

Input conductance	g_{ib}	typ.	125 mS
Input capacitance	C_{ib}	typ.	64 pF
Transfer admittance	$\|y_{fb}\|$	typ.	100 mS
Phase angle of transfer admittance	φ_{fb}	typ.	147°
Output conductance	g_{ob}	typ.	40 μS
Output capacitance	C_{ob}	typ.	1,25 pF
Feedback admittance	$\|y_{rb}\|$	typ.	220 μS
Phase angle of feedback admittance	φ_{rb}	typ.	85°

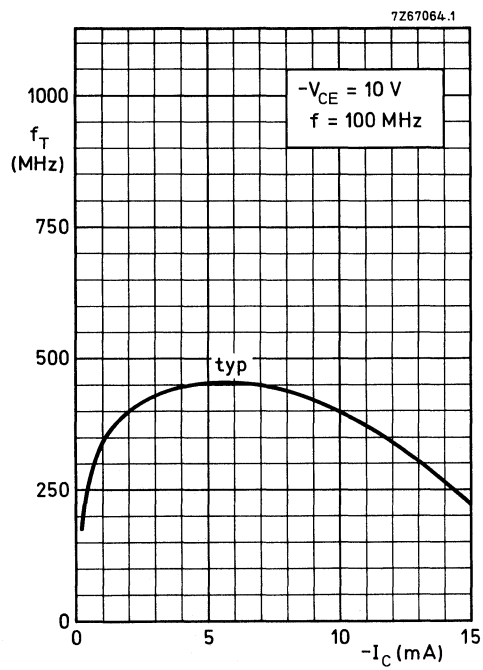


Fig. 2.

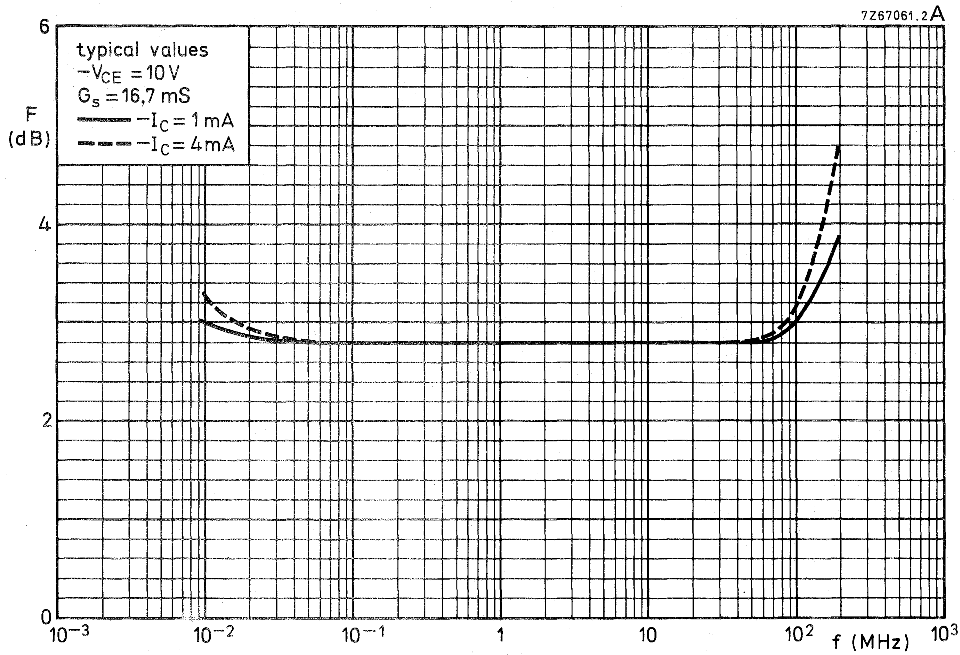


Fig. 3.

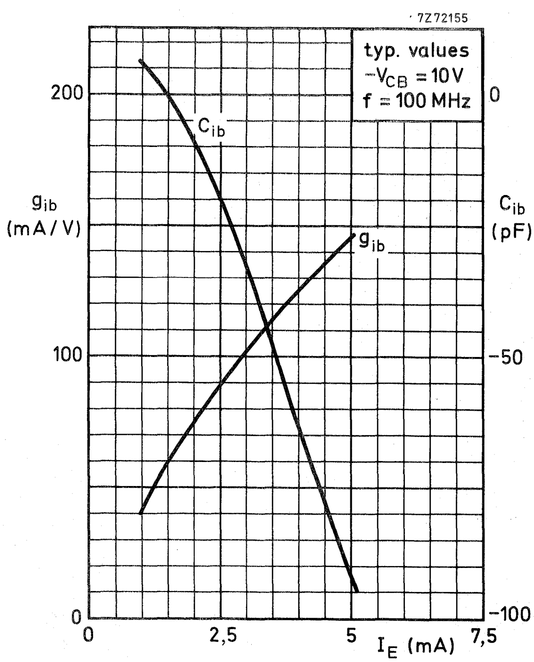


Fig. 4.

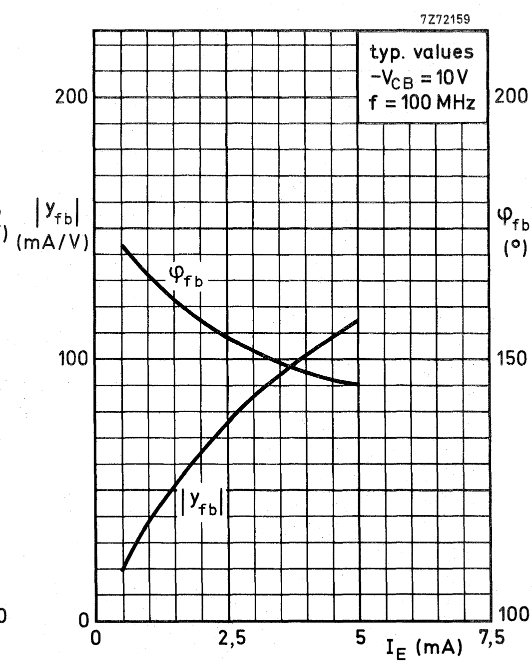


Fig. 5.

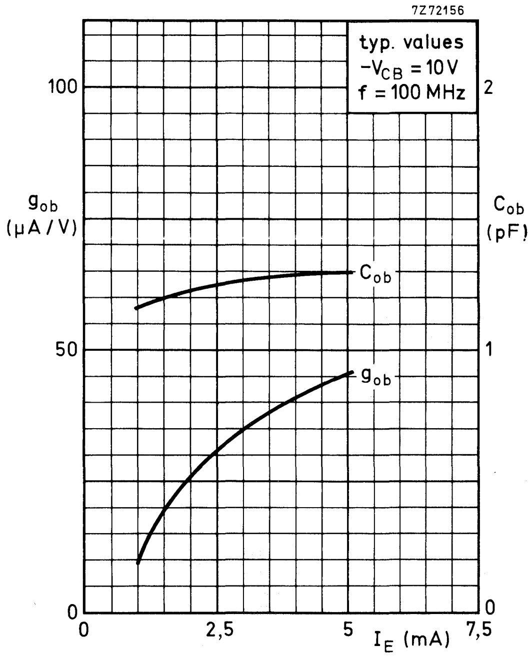


Fig. 6.

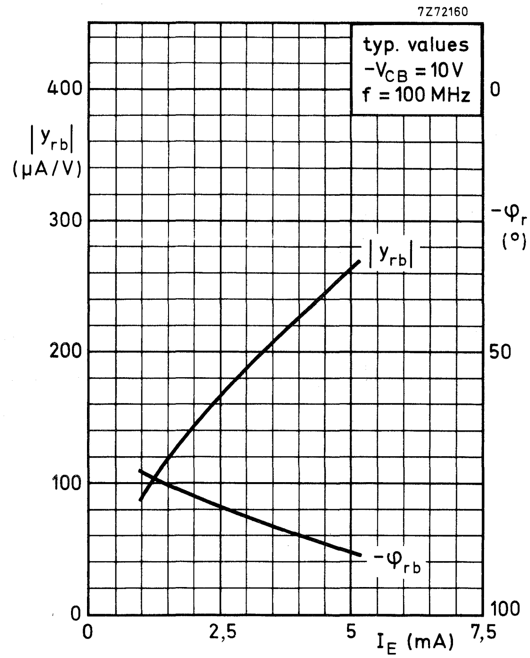


Fig. 7.

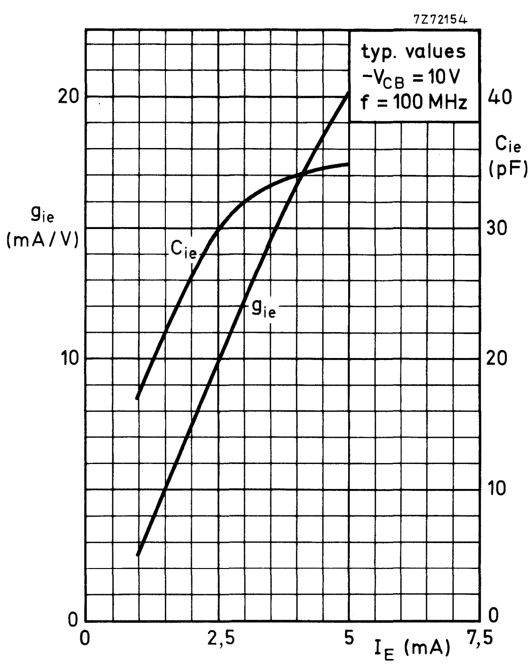


Fig. 8.

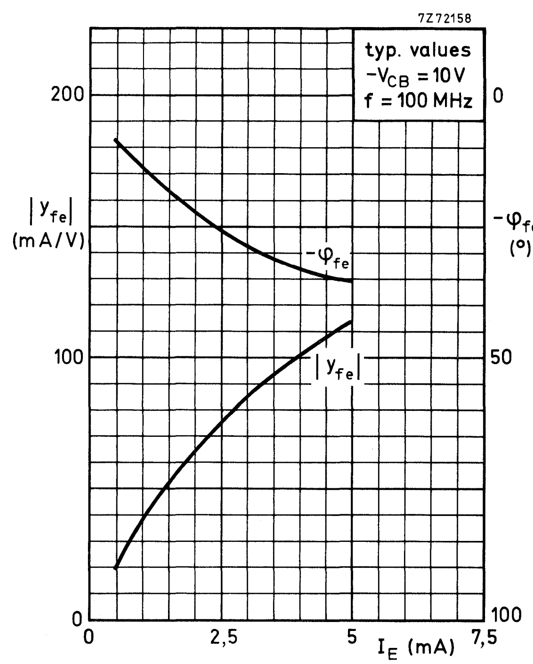


Fig. 9.

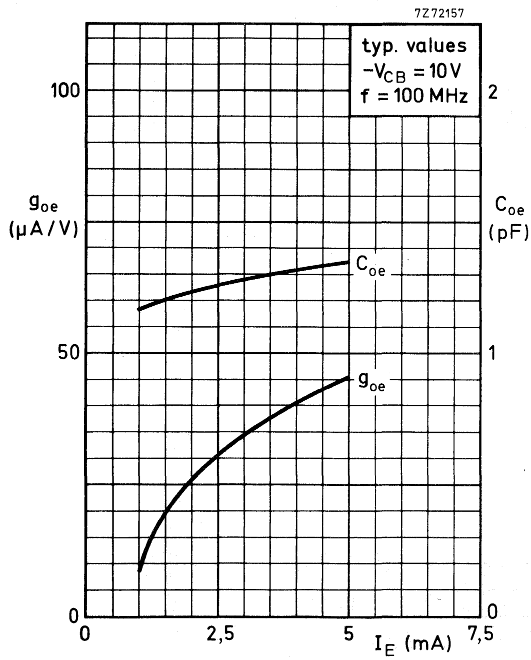

7Z72157
typ. values
$-V_{CB} = 10$ V
f = 100 MHz
g_{oe}
(μA/V)
C_{oe}
(pF)
100
50
0
2
1
0
0
2,5
5
7,5
I_E (mA)

Fig. 10.

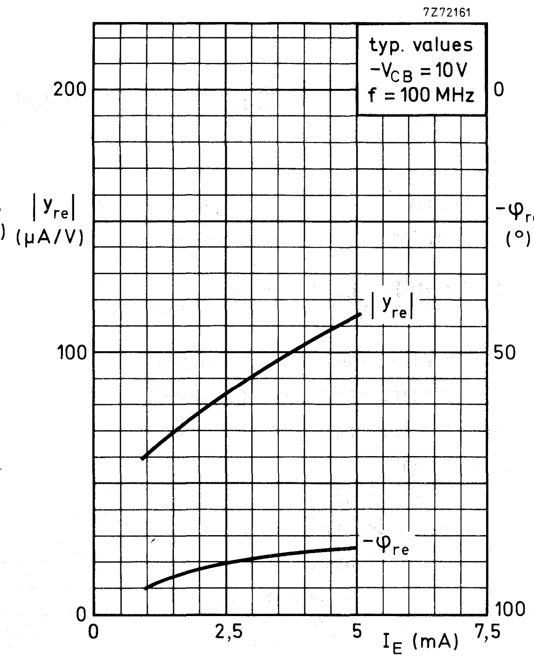

7Z72161
typ. values
$-V_{CB} = 10$ V
f = 100 MHz
$|y_{re}|$
(μA/V)
$-\varphi_{re}$
(°)
200
100
0
0
50
100
0
2,5
5
7,5
I_E (mA)

Fig. 11.

SILICON PLANAR TRANSISTORS

N-P-N transistors in a plastic SOT-23 envelope.

Primarily intended for a.m. mixers and i.f. amplifiers in a.m./f.m. receivers using SMD technology.

QUICK REFERENCE DATA

			BF840	BF841	
Collector-base voltage (open emitter)	V_{CBO}	max.	40		V
Collector-emitter voltage (open base)	V_{CEO}	max.	40		V
Collector current (d.c.)	I_C	max.	25		mA
Base current I_C = 1 mA; V_{CE} = 10 V	I_B		4,5–15	8–28	μA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300		mW
Junction temperature	T_j	max.	150		°C
Feedback capacitance at f = 1 MHz I_C = 1 mA; V_{CE} = 10 V	C_{re}	typ.	0,3		pF

MECHANICAL DATA

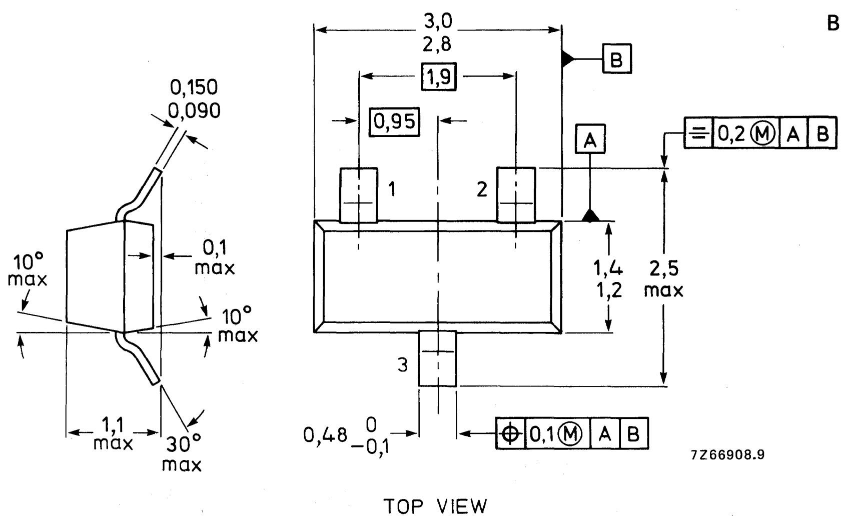
Fig. 1 SOT-23.

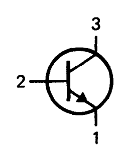
Dimensions in mm

Marking code:

BF840 : F3

BF841 : F31





See also Soldering recommendations.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	V_{CBO}	max.	40 V
Collector-emitter voltage (open base)	V_{CEO}	max.	40 V
Emitter-base voltage (open collector)	V_{EBO}	max.	4 V
Collector current (d.c.)	I_C	max.	25 mA
Total power dissipation up to T_{amb} = 25 °C*	P_{tot}	max.	300 mW
Storage temperature	T_{stg}		−55 to +150 °C
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j-a}$	=	430 K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current I_E = 0; V_{CB} = 20 V	I_{CBO}	max.	100 nA
Base-emitter voltage I_C = 1 mA; V_{CE} = 10 V	V_{BE}	typ. 	700 mV 650 to 740 mV

			BF840	BF841	
Base current I_C = 1 mA; V_{CE} = 10 V	I_B		4,5–15	8–28	μA
Transition frequency at f = 100 MHz I_C = 1 mA; V_{CE} = 10 V	f_T	typ.	380	380	MHz
Feedback capacitance at f = 1 MHz I_C = 1 mA; V_{CE} = 10 V	C_{re}	typ.	0,3	0,3	pF
Noise figure I_C = 1 mA; V_{CE} = 10 V; f = 0,2 MHz; R_S = 200 Ω	F	typ.	1,5	2,0	dB

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

SILICON N-CHANNEL DUAL GATE MOS-FET

Depletion type field-effect transistor in a plastic SOT-143 microminiature envelope with source and substrate interconnected. This MOS-FET tetrode is intended for use in u.h.f. applications in television tuners. The device is also suitable for use in professional communication equipment.

The device is protected against excessive input voltage surges by integrated back-to-back diodes between gates and source.

QUICK REFERENCE DATA

Drain-source voltage	V_{DS}	max.	20	V
Drain current (peak value)	I_{DM}	max.	30	mA
Total power dissipation up to T_{amb} = 60 °C	P_{tot}	max.	200	mW
Junction temperature	T_j	max.	150	°C
Transfer admittance at f = 1 kHz I_D = 7 mA; V_{DS} = 10 V; + $V_{G2\text{-}S}$ = 4 V	$\|y_{fs}\|$	typ.	12	mS
Feedback capacitance at f = 1 MHz I_D = 7 mA; V_{DS} = 10 V; + $V_{G2\text{-}S}$ = 4 V	C_{rs}	typ.	25	fF
Noise figure at G_S = 2 mS I_D = 7 mA; V_{DS} = 10 V; + $V_{G2\text{-}S}$ = 4 V; f = 800 MHz	F	typ.	2,8	dB

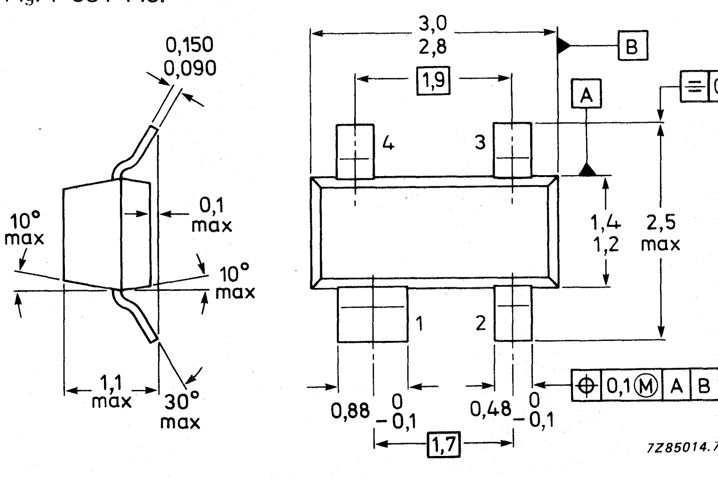
MECHANICAL DATA

Dimensions in mm

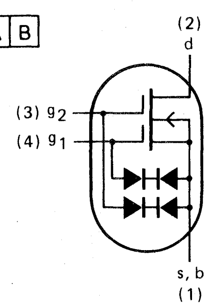
Marking code

BF989 = M89

Fig. 1 SOT-143.



TOP VIEW



See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	V_{DS}	max.	20 V
Drain current (d.c. or average)	I_D	max.	20 mA
Drain current (peak value)	I_{DM}	max.	30 mA
Gate 1 - source current	$\pm I_{G1-S}$	max.	10 mA
Gate 2 - source current	$\pm I_{G2-S}$	max.	10 mA
Total power dissipation up to T_{amb} = 60 °C*	P_{tot}	max.	200 mW
Storage temperature	T_{stg}		–65 to + 150 °C
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE

From junction to ambient in free air*	$R_{th\ j-a}$	=	460 K/W

STATIC CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Gate cut-off currents			
$\pm V_{G1-S} = 5$ V; $V_{G2-S} = V_{DS} = 0$	$\pm I_{G1-SS}$	<	50 nA
$\pm V_{G2-S} = 5$ V; $V_{G1-S} = V_{DS} = 0$	$\pm I_{G2-SS}$	<	50 nA
Drain current			
$V_{DS} = 10$ V; $V_{G1-S} = 0$; $+V_{G2-S} = 4$ V; $T_j = 25$ °C	I_{DSS}		2 to 20 mA
Gate-source breakdown voltages			
$\pm I_{G1-SS} = 10$ mA; $V_{G2-S} = V_{DS} = 0$	$\pm V_{(BR)G1-SS}$		6 to 20 V
$\pm I_{G2-SS} = 10$ mA; $V_{G1-S} = V_{DS} = 0$	$\pm V_{(BR)G2-SS}$		6 to 20 V
Gate-source cut-off voltages			
$I_D = 20\ \mu$A; $V_{DS} = 10$ V; $+V_{G2-S} = 4$ V	$-V_{(P)G1-S}$	<	2,7 V
$I_D = 20\ \mu$A; $V_{DS} = 10$ V; $V_{G1-S} = 0$	$-V_{(P)G2-S}$	<	2,7 V

DYNAMIC CHARACTERISTICS

Measuring conditions (common source): $I_D = 7$ mA; $V_{DS} = 10$ V; $+V_{G2-S} = 4$ V; $T_{amb} = 25$ °C

Transfer admittance at f = 1 kHz	$\lvert y_{fs} \rvert$	>	9,5 mS
		typ.	12 mS
Input capacitance at gate 1; f = 1 MHz	C_{ig1-s}	typ.	1,8 pF
Input capacitance at gate 2; f = 1 MHz	C_{ig2-s}	typ.	1,0 pF
Feedback capacitance at f = 1 MHz	C_{rs}	typ.	25 fF
Output capacitance at f = 1 MHz	C_{os}	typ.	0,9 pF
Noise figure at G_S = 2 mS			
f = 200 MHz	F	typ.	1,6 dB
f = 800 MHz	F	typ.	2,8 dB

* Device mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

SILICON N-CHANNEL DUAL GATE MOS-FET

Depletion type field-effect transistor in a plastic microminiature envelope with source and substrate interconnected, intended for u.h.f. applications, such as u.h.f. television tuners and professional communication equipment.

This MOS-FET tetrode is protected against excessive input voltage surges by integrated back-to-back diodes between gates and source.

QUICK REFERENCE DATA

Drain-source voltage	V_{DS}	max.	18	V
Drain current (average)	$I_{D(AV)}$	max.	30	mA
Total power dissipation up to T_{amb} = 60 °C	P_{tot}	max.	200	mW
Junction temperature	T_j	max.	150	°C
Transfer admittance at f = 1 kHz I_D = 10 mA; V_{DS} = 10 V; + $V_{G2\text{-}S}$ = 4 V	$\lvert y_{fs} \rvert$	typ.	19	mS
Feedback capacitance at f = 1 MHz I_D = 10 mA; V_{DS} = 10 V; + $V_{G2\text{-}S}$ = 4 V	C_{rs}	typ.	25	fF
Noise figure at optimum source admittance I_D = 10 mA; V_{DS} = 10 V; + $V_{G2\text{-}S}$ = 4 V; f = 800 MHz	F	typ.	2,8	dB

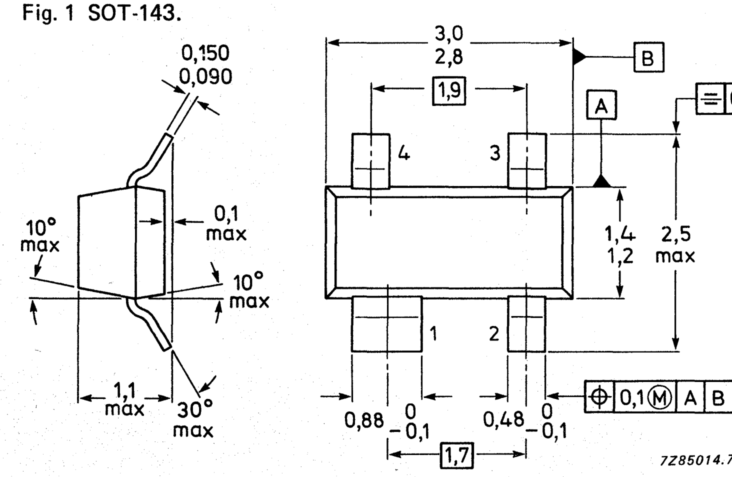
MECHANICAL DATA

Dimensions in mm

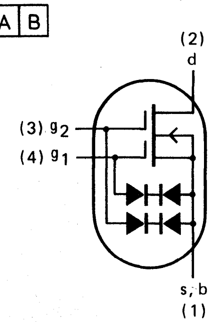
Marking code

BF990 = M90

Fig. 1 SOT-143.



TOP VIEW



See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	V_{DS}	max.	18	V
Drain current (average)	$I_{D(AV)}$	max.	30	mA
Gate 1-source current	$\pm I_{G1\text{-}S}$	max.	10	mA
Gate 2-source current	$\pm I_{G2\text{-}S}$	max.	10	mA
Total power dissipation up to T_{amb} = 60 °C*	P_{tot}	max.	200	mW
Storage temperature	T_{stg}		−65 to + 150	°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE

From junction to ambient in free air*	$R_{th\ j\text{-}a}$	=	460	K/W

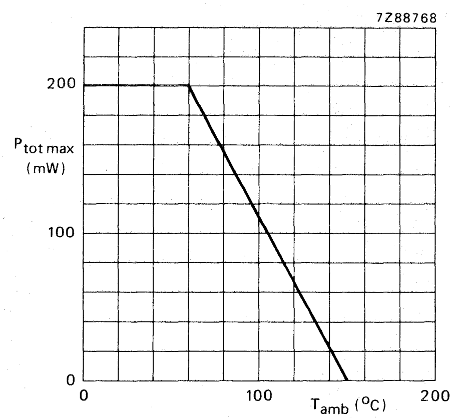


Fig. 2 Power derating curve.

* Device mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

STATIC CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Gate cut-off currents			
gate 1; $\pm V_{G1\text{-}S} = 7$ V; $V_{G2\text{-}S} = V_{DS} = 0$	$\pm I_{G1\text{-}SS}$	<	25 nA
gate 2; $\pm V_{G2\text{-}S} = 7$ V; $V_{G1\text{-}S} = V_{DS} = 0$	$\pm I_{G2\text{-}SS}$	<	25 nA
Gate-source breakdown voltages			
gate 1; $\pm I_{G1\text{-}SS} = 10$ mA; $V_{G2\text{-}S} = V_{DS} = 0$	$\pm V_{(BR)G1\text{-}SS}$	>	8 V
gate 2; $\pm I_{G2\text{-}SS} = 10$ mA; $V_{G1\text{-}S} = V_{DS} = 0$	$\pm V_{(BR)G2\text{-}SS}$	>	8 V
Gate-source cut-off voltages			
gate 1; $I_D = 20\ \mu$A; $V_{DS} = 10$ V; $+V_{G2\text{-}S} = 4$ V	$-V_{(P)G1\text{-}S}$	<	1,3 V
gate 2; $I_D = 20\ \mu$A; $V_{DS} = 10$ V; $V_{G1\text{-}S} = 0$	$-V_{(P)G2\text{-}S}$	<	1,1 V

DYNAMIC CHARACTERISTICS

Measuring conditions (common source): $I_D = 10$ mA; $V_{DS} = 10$ V; $+V_{G2\text{-}S} = 4$ V; $T_{amb} = 25$ °C

Transfer admittance at f = 1 kHz	$\|y_{fs}\|$	>	17 mS
		typ.	19 mS
Input capacitance at gate 1; f = 1 MHz	$C_{ig1\text{-}s}$	typ.	2,6 pF
		<	3,0 pF
Input capacitance at gate 2; f = 1 MHz	$C_{ig2\text{-}s}$	typ.	1,4 pF
Feedback capacitance at f = 1 MHz	C_{rs}	typ.	25 fF
Output capacitance at f = 1 MHz	C_{os}	typ.	1,2 pF
Noise figure at f = 800 MHz; G_S = 5 mS	F	typ.	2,8 dB

SILICON N-CHANNEL DUAL GATE MOS-FET

Depletion type field-effect transistor in a plastic SOT-143 microminiature envelope with source and substrate interconnected. This MOS-FET tetrode is intended for use in v.h.f. applications, such as v.h.f. television tuners and f.m. tuners. The device is also suitable for use in professional communication equipment.

The device is protected against excessive input voltage surges by integrated back-to-back diodes between gates and source.

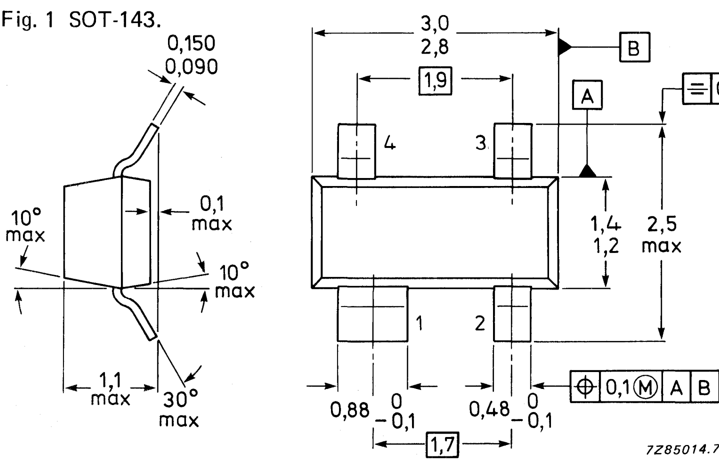
QUICK REFERENCE DATA

Drain-source voltage	V_{DS}	max.	20	V
Drain current	I_D	max.	20	mA
Total power dissipation up to T_{amb} = 60 °C	P_{tot}	max.	200	mW
Junction temperature	T_j	max.	150	°C
Transfer admittance at f = 1 kHz I_D = 10 mA; V_{DS} = 10 V; + V_{G2-S} = 4 V	$\|y_{fs}\|$	typ.	14	mS
Feedback capacitance at f = 1 MHz I_D = 10 mA; V_{DS} = 10 V; + V_{G2-S} = 4 V	C_{rs}	typ.	20	fF
Noise figure at optimum source admittance I_D = 10 mA; V_{DS} = 10 V; + V_{G2-S} = 4 V; f = 200 MHz	F	typ.	0,7	dB

MECHANICAL DATA

Dimensions in mm

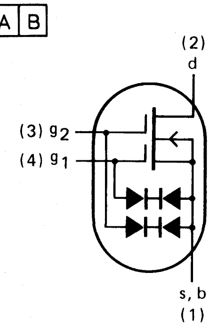
Fig. 1 SOT-143.



TOP VIEW

Marking code

BF991 = M91



See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	V_{DS}	max.	20 V
Drain current (d.c. or average)	I_D	max.	20 mA
Drain current (peak value)	I_{DM}	max.	30 mA
Gate 1 - source current	$\pm I_{G1\text{-}S}$	max.	10 mA
Gate 2 - source current	$\pm I_{G2\text{-}S}$	max.	10 mA
Total power dissipation up to $T_{amb} = 60\ ^oC$*	P_{tot}	max.	200 mW
Storage temperature	T_{stg}	−65 to + 150	^oC
Junction temperature	T_j	max.	150 ^oC

THERMAL RESISTANCE

From junction to ambient in free air*	$R_{th\ j\text{-}a}$	=	460 K/W

STATIC CHARACTERISTICS

$T_{amb} = 25\ ^oC$ unless otherwise specified

Gate cut-off currents			
$\pm V_{G1\text{-}S} = 5$ V; $V_{G2\text{-}S} = V_{DS} = 0$	$\pm I_{G1\text{-}SS}$	<	50 nA
$\pm V_{G2\text{-}S} = 5$ V; $V_{G1\text{-}S} = V_{DS} = 0$	$\pm I_{G2\text{-}SS}$	<	50 nA
Drain current			
$V_{DS} = 10$ V; $V_{G1\text{-}S} = 0$; $+ V_{G2\text{-}S} = 4$ V; $T_j = 25\ ^oC$	I_{DSS}		4 to 25 mA
Gate-source breakdown voltages			
$\pm I_{G1\text{-}SS} = 10$ mA; $V_{G2\text{-}S} = V_{DS} = 0$	$\pm V_{(BR)G1\text{-}SS}$	>	6 V
$\pm I_{G2\text{-}SS} = 10$ mA; $V_{G1\text{-}S} = V_{DS} = 0$	$\pm V_{(BR)G2\text{-}SS}$	>	6 V
Gate-source cut-off voltages			
$I_D = 20\ \mu A$; $V_{DS} = 10$ V; $+ V_{G2\text{-}S} = 4$ V	$-V_{(P)G1\text{-}S}$	<	2,5 V
$I_D = 20\ \mu A$; $V_{DS} = 10$ V; $V_{G1\text{-}S} = 0$	$-V_{(P)G2\text{-}S}$	<	2,5 V

DYNAMIC CHARACTERISTICS

Measuring conditions (common source): $I_D = 10$ mA; $V_{DS} = 10$ V; $+ V_{G2\text{-}S} = 4$ V; $T_{amb} = 25\ ^oC$

Transfer admittance at f = 1 kHz	$\lvert y_{fs} \rvert$	>	10 mS
		typ.	14 mS
Input capacitance at gate 1; f = 1 MHz	$C_{ig1\text{-}s}$	typ.	2,1 pF
Input capacitance at gate 2; f = 1 MHz	$C_{ig2\text{-}s}$	typ.	1,0 pF
Feedback capacitance at f = 1 MHz	C_{rs}	typ.	20 fF
Output capacitance at f = 1 MHz	C_{os}	typ.	1,1 pF
Noise figure			
f = 100 MHz; $G_S = 1$ mS	F	typ.	0,7 dB
		<	1,7 dB
f = 200 MHz; $G_S = 2$ mS	F	typ.	1,0 dB
		<	2,0 dB
Transducer gain **			
f = 100 MHz; $G_S = 1$ mS; $G_L = 0,5$ mS	G_{tr}	typ.	29 dB
f = 200 MHz; $G_S = 2$ mS; $G_L = 0,5$ mS	G_{tr}	typ.	26 dB

* Device mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

** Crystal mounted in a SOT-103 envelope.

SILICON N-CHANNEL DUAL GATE MOS-FET

Depletion type field-effect transistor in a plastic SOT-143 microminiature envelope with source and substrate interconnected. This MOS-FET tetrode is intended for use in v.h.f. applications, such as v.h.f. television tuners, FM tuners with a 12 volt supply voltage. The device is also suitable for use in professional communication equipment.

The device is protected against excessive input voltage surges by integrated back-to-back diodes between gates and source.

QUICK REFERENCE DATA

Drain-source voltage	V_{DS}	max.	20	V
Drain current	I_D	max.	40	mA
Total power dissipation up to T_{amb} = 60 °C	P_{tot}	max.	200	mW
Junction temperature	T_j	max.	150	°C
Transfer admittance at f = 1 kHz I_D = 15 mA; V_{DS} = 10 V; + $V_{G2\text{-}S}$ = 4 V	$\lvert y_{fs} \rvert$	typ.	25	mS
Feedback capacitance at f = 1 MHz I_D = 15 mA; V_{DS} = 10 V; + $V_{G2\text{-}S}$ = 4 V	C_{rs}	typ.	30	fF
Noise figure at G_S = 2 mS I_D = 15 mA; V_{DS} = 10 V; + $V_{G2\text{-}S}$ = 4 V; f = 200 MHz	F	typ.	1,2	dB

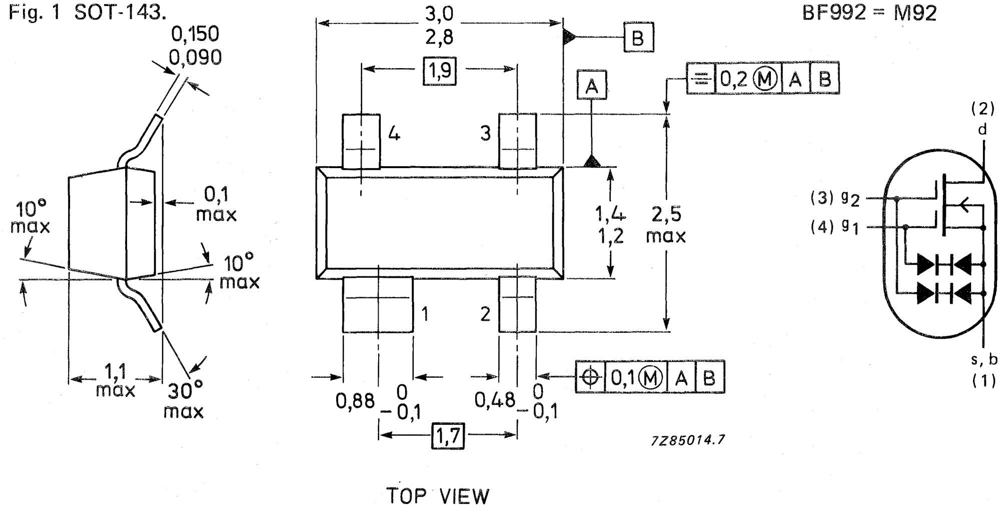
MECHANICAL DATA

Dimensions in mm

Marking code

BF992 = M92

Fig. 1 SOT-143.



See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	V_{DS}	max.	20 V
Drain current (d.c. or average)	I_D	max.	40 mA
Gate 1 - source current	$\pm I_{G1-S}$	max.	10 mA
Gate 2 - source current	$\pm I_{G2-S}$	max.	10 mA
Total power dissipation up to T_{amb} = 60 °C*	P_{tot}	max.	200 mW
Storage temperature	T_{stg}	−65 to + 150 °C	
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE

From junction to ambient in free air*	$R_{th\ j\text{-}a}$	=	460 K/W

STATIC CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Gate cut-off currents			
$\pm V_{G1-S} = 7$ V; $V_{G2-S} = V_{DS} = 0$	$\pm I_{G1-SS}$	<	25 nA
$\pm V_{G2-S} = 7$ V; $V_{G1-S} = V_{DS} = 0$	$\pm I_{G2-SS}$	<	25 nA
Gate-source breakdown voltages			
$\pm I_{G1-SS} = 10$ mA; $V_{G2-S} = V_{DS} = 0$	$\pm V_{(BR)G1-SS}$	>	8 V
$\pm I_{G2-SS} = 10$ mA; $V_{G1-S} = V_{DS} = 0$	$\pm V_{(BR)G2-SS}$	>	8 V
Gate-source cut-off voltages			
$I_D = 20\ \mu$A; $V_{DS} = 10$ V; $+V_{G2-S} = 4$ V	$-V_{(P)G1-S}$		0,2 to 1,3 V
$I_D = 20\ \mu$A; $V_{DS} = 10$ V; $V_{G1-S} = 0$	$-V_{(P)G2-S}$		0,2 to 1,1 V

DYNAMIC CHARACTERISTICS

Measuring conditions (common source): $I_D = 15$ mA; $V_{DS} = 10$ V; $+V_{G2-S} = 4$ V; $T_{amb} = 25$ °C

Transfer admittance at f = 1 kHz	$\|y_{fs}\|$	>	20 mS
		typ.	25 mS
Input capacitance at gate 1; f = 1 MHz	C_{ig1-s}	typ.	4 pF
Input capacitance at gate 2; f = 1 MHz	C_{ig2-s}	typ.	1,7 pF
Feedback capacitance at f = 1 MHz	C_{rs}	typ.	30 fF
		<	40 fF
Output capacitance at f = 1 MHz	C_{os}	typ.	2 pF
Noise figure at f = 200 MHz; $G_S = 2$ mS	F	typ.	1,2 dB

→ * Device mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

SILICON N-CHANNEL DUAL GATE MOS-FET

Depletion type field-effect transistor in a plastic microminiature envelope with source and substrate interconnected, intended for u.h.f. and v.h.f. applications, such as u.h.f./v.h.f. television tuners and professional communication equipment.

This MOS-FET tetrode is protected against excessive input voltage surges by integrated back-to-back diodes between gates and source.

QUICK REFERENCE DATA

Drain-source voltage	V_{DS}	max.	20	V
Drain current (average)	$I_{D(AV)}$	max.	30	mA
Total power dissipation up to T_{amb} = 60 °C	P_{tot}	max.	200	mW
Junction temperature	T_j	max.	150	°C
Transfer admittance at f = 1 kHz I_D = 10 mA; V_{DS} = 15 V; + $V_{G2\text{-}S}$ = 4 V	$\|y_{fs}\|$	typ.	17	mS
Feedback capacitance at f = 1 MHz I_D = 10 mA; V_{DS} = 15 V; + $V_{G2\text{-}S}$ = 4 V	C_{rs}	typ.	25	fF
Noise figure at optimum source admittance I_D = 10 mA; V_{DS} = 15 V; + $V_{G2\text{-}S}$ = 4 V; f = 200 MHz	F	typ.	1,5	dB

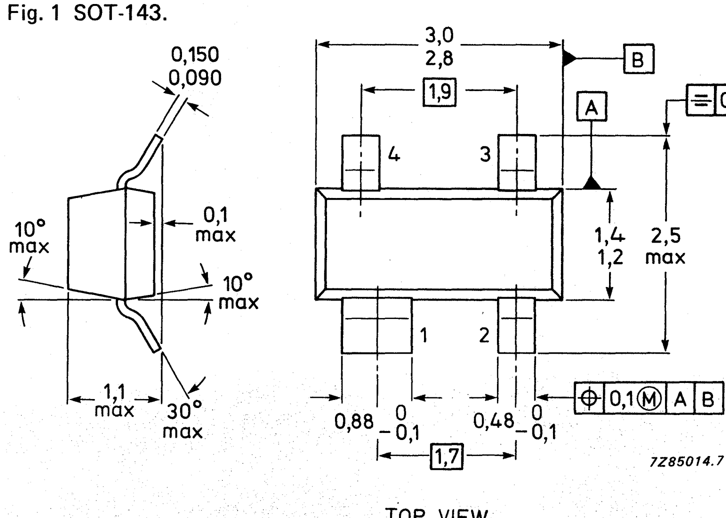
MECHANICAL DATA

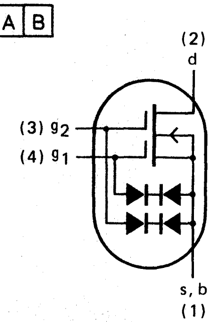
Dimensions in mm

Marking code

BF994 = M94

Fig. 1 SOT-143.





See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	V_{DS}	max.	20 V
Drain current (average)	$I_{D(AV)}$	max.	30 mA
Gate 1-source current	$\pm I_{G1\text{-}S}$	max.	10 mA
Gate 2-source current	$\pm I_{G2\text{-}S}$	max.	10 mA
Total power dissipation up to T_{amb} = 60 °C*	P_{tot}	max.	200 mW
Storage temperature	T_{stg}	−65 to + 150 °C	
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE

From junction to ambient in free air*	$R_{th\,j\text{-}a}$	=	460 K/W

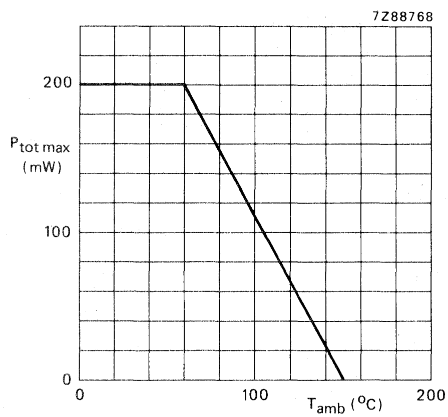


Fig. 2 Power derating curve.

* Device mounted on a ceramic substrate of 8 mm x 10 mm x 0,6 mm.

STATIC CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Gate cut-off currents			
gate 1; $\pm V_{G1\text{-}S}$ = 5 V; $V_{G2\text{-}S} = V_{DS} = 0$	$\pm I_{G1\text{-}SS}$	<	50 nA
gate 2; $\pm V_{G2\text{-}S}$ = 5 V; $V_{G1\text{-}S} = V_{DS} = 0$	$\pm I_{G2\text{-}SS}$	<	50 nA
Gate-source breakdown voltages			
gate 1; $\pm I_{G1\text{-}SS}$ = 10 mA; $V_{G2\text{-}S} = V_{DS} = 0$	$\pm V_{(BR)G1\text{-}SS}$		6 to 20 V
gate 2; $\pm I_{G2\text{-}SS}$ = 10 mA; $V_{G1\text{-}S} = V_{DS} = 0$	$\pm V_{(BR)G2\text{-}SS}$		6 to 20 V
Gate-source cut-off voltages			
gate 1; I_D = 20 μA; V_{DS} = 15 V; $+V_{G2\text{-}S}$ = 4 V	$-V_{(P)G1\text{-}S}$	<	2,5 V
gate 2; I_D = 20 μA; V_{DS} = 15 V; $V_{G1\text{-}S}$ = 0	$-V_{(P)G2\text{-}S}$	<	2,0 V
Drain-source cut-off voltage V_{DS} = 15 V; $V_{G2\text{-}S}$ = 4 V	I_{DSS}		2 to 20 mA

DYNAMIC CHARACTERISTCS

Measuring conditions (common source): I_D = 10 mA; V_{DS} = 15 V; $+V_{G2\text{-}S}$ = 4 V; T_{amb} = 25 °C

Transfer admittance at f = 1 kHz	$\lvert y_{fs} \rvert$	>	15 mS
		typ.	17 mS
Input capacitance at gate 1; f = 1 MHz	$C_{ig1\text{-}s}$	typ.	2,5 pF
Input capacitance at gate 2; f = 1 MHz	$C_{ig2\text{-}s}$	typ.	1,2 pF
Feedback capacitance at f = 1 MHz	C_{rs}	typ.	25 fF
Output capacitance at f = 1 MHz	C_{os}	typ.	1,0 pF
Noise figure at f = 200 MHz; G_S = 2 mS	F	typ.	1,5 dB
		<	2,8 dB
Power gain at G_S = 2 mS, G_L = 0,5 mS, f = 200 MHz	G_p	typ.	25 dB

SILICON N-CHANNEL DUAL GATE MOS-FET

Depletion type field-effect transistor in a plastic microminiature envelope (SOT-143) with source and substrate interconnected and intended for v.h.f. applications in television tuners, using SMD* technology. The device is also suitable for use in professional communication equipment.

This MOS-FET tetrode is protected against excessive input voltage surges by integrated back-to-back diodes between gates and source.

* Surface Mounted Devices.

QUICK REFERENCE DATA

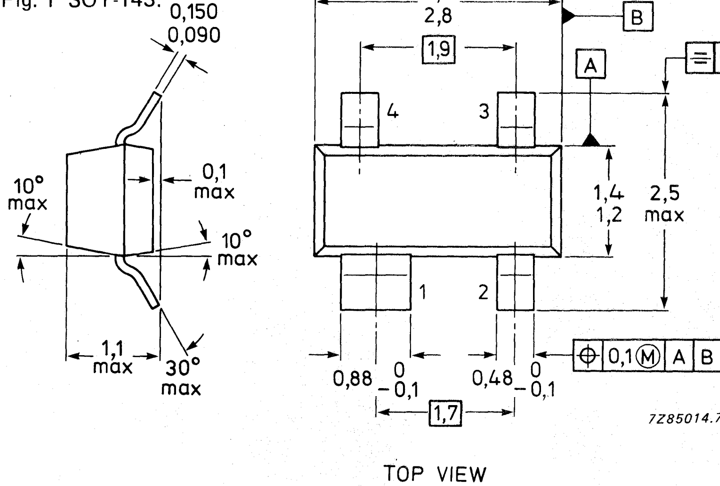
Drain-source voltage	V_{DS}	max.	20	V
Drain current	I_D	max.	50	mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300	mW
Junction temperature	T_j	max.	150	°C
Transfer admittance at f = 1 kHz I_D = 10 mA; V_{DS} = 15 V; $+V_{G2\text{-}S}$ = 4 V	$\lvert y_{fs} \rvert$	typ.	18	mS
Feedback capacitance at f = 1 MHz I_D = 10 mA; V_{DS} = 15 V; $+V_{G2\text{-}S}$ = 4 V	C_{rs}	typ.	25	fF
Noise figure at G_S = 2 mS I_D = 10 mA; V_{DS} = 15 V; $+V_{G2\text{-}S}$ = 4 V; f = 200 MHz	F	typ.	1,0	dB

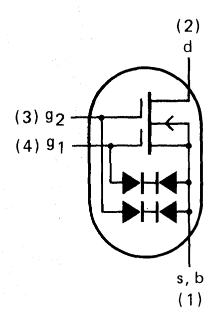
MECHANICAL DATA

Dimensions in mm

Marking code
BF994S = M93

Fig. 1 SOT-143.





RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	V_{DS}	max.	20 V
Drain current (d.c. or average)	I_D	max.	50 mA
Gate 1 - source current	$\pm I_{G1\text{-}S}$	max.	10 mA
Gate 2 - source current	$\pm I_{G2\text{-}S}$	max.	10 mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300 mW
Storage temperature	T_{stg}		−65 to 150 °C
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE

From junction to ambient in free air mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm	$R_{th\ j\text{-}a}$	=	430 K/W

STATIC CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Gate cut-off currents			
$\pm V_{G1\text{-}S}$ = 5 V; $V_{G2\text{-}S} = V_{DS}$ = 0	$\pm I_{G1\text{-}S}$	<	50 nA
$\pm V_{G2\text{-}S}$ = 5 V; $V_{G1\text{-}S} = V_{DS}$ = 0	$\pm I_{G2\text{-}S}$	<	50 nA
Gate-source breakdown voltages			
$\pm I_{G1\text{-}S}$ = 10 mA; $V_{G2\text{-}S} = V_{DS}$ = 0	$\pm V_{(BR)G1\text{-}SS}$		6,0 to 20 V
$\pm I_{G2\text{-}S}$ = 10 mA; $V_{G1\text{-}S} = V_{DS}$ = 0	$\pm V_{(BR)G2\text{-}SS}$		6,0 to 20 V
Drain current			
V_{DS} = 15 V; $V_{G1\text{-}S}$ = 0; $V_{G2\text{-}S}$ = 4 V	I_{DSS}		4 to 20 mA
Gate-source cut-off voltages			
I_D = 20 μA; V_{DS} = 15 V; $+V_{G2\text{-}S}$ = 4 V	$-V_{(P)G1\text{-}S}$	<	2,5 V
I_D = 20 μA; V_{DS} = 15 V; $V_{G1\text{-}S}$ = 0	$-V_{(P)G2\text{-}S}$	<	2,0 V

DYNAMIC CHARACTERISTICS

Measuring conditions (common source): I_D = 10 mA; V_{DS} = 15 V; $+V_{G2\text{-}S}$ = 4 V; T_{amb} = 25 °C.

Transfer admittance at f = 1 kHz	$\lvert y_{fs} \rvert$	>	15 mS
		typ.	18 mS
Input capacitance at gate 1: f = 1 MHz	$C_{ig1\text{-}s}$	typ.	2,5 pF
		<	3,0 pF
Input capacitance at gate 2: f = 1 MHz	$C_{ig2\text{-}s}$	typ.	1,2 pF
Feedback capacitance at f = 1 MHz	C_{rs}	typ.	25 fF
Output capacitance at f = 1 MHz	C_{os}	typ.	1,0 pF
Noise figure at G_S = 2 mS and f = 200 MHz	F	typ.	1,0 dB
Power gain at G_S = 2 mS, G_L = 0,5 mS; f = 200 MHz	G_p	typ.	25 dB

SILICON N-CHANNEL DUAL GATE MOS-FET

Depletion type field-effect transistor in a plastic microminiature envelope, with source and substrate interconnected, intended for u.h.f. applications, such as television tuners and professional communication equipment.

This MOS-FET tetrode is protected against excessive input voltage surges by integrated back-to-back diodes between gates and source.

QUICK REFERENCE DATA

Drain-source voltage	V_{DS}	max.	20	V
Drain current (average)	$I_{D(AV)}$	max.	30	mA
Total power dissipation up to T_{amb} = 60 °C	P_{tot}	max.	200	mW
Junction temperature	T_j	max.	150	°C
Transfer admittance at f = 1 kHz I_D = 10 mA; V_{DS} = 15 V; + $V_{G2\text{-}S}$ = 4 V	$\lvert y_{fs} \rvert$	typ.	17	mS
Feedback capacitance at f = 1 MHz I_D = 10 mA; V_{DS} = 15 V; + $V_{G2\text{-}S}$ = 4 V	C_{rs}	typ.	25	fF
Noise figure at optimum source admittance I_D = 10 mA; V_{DS} = 10 V; + $V_{G2\text{-}S}$ = 4 V; f = 800 MHz	F	typ.	2,8	dB
I_D = 10 mA; V_{DS} = 15 V; + $V_{G2\text{-}S}$ = 4 V; f = 200 MHz	F	typ.	1,5	dB

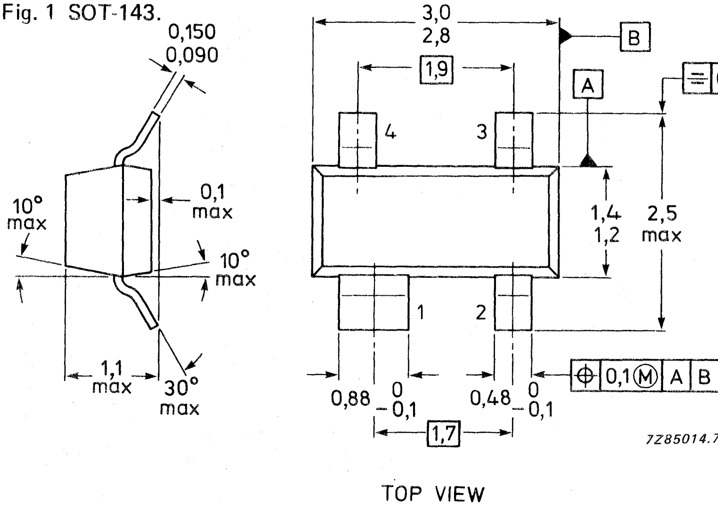
MECHANICAL DATA

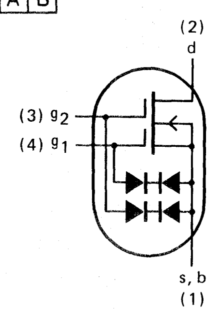
Dimensions in mm

Marking code

BF996 = M96

Fig. 1 SOT-143.





See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	V_{DS}	max.	20 V
Drain current (average)	$I_{D(AV)}$	max.	30 mA
Gate 1-source current	$\pm I_{G1\text{-}S}$	max.	10 mA
Gate 2-source current	$\pm I_{G2\text{-}S}$	max.	10 mA
Total power dissipation up to T_{amb} = 60 °C*	P_{tot}	max.	200 mW
Storage temperature	T_{stg}	−65 to + 150 °C	
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE

From junction to ambient in free air*	$R_{th\ j\text{-}a}$	=	460 K/W

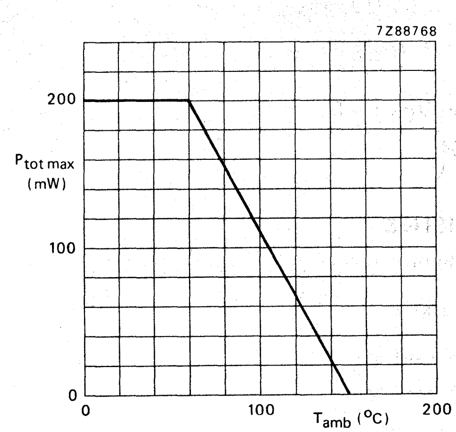


Fig. 2 Power derating curve.

* Device mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

STATIC CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Gate cut-off currents			
gate 1; $\pm V_{G1\text{-}S}$ = 5 V; $V_{G2\text{-}S} = V_{DS} = 0$	$\pm I_{G1\text{-}SS}$	<	50 nA
gate 2; $\pm V_{G2\text{-}S}$ = 5 V; $V_{G1\text{-}S} = V_{DS} = 0$	$\pm I_{G2\text{-}SS}$	<	50 nA
Gate-source breakdown voltages			
gate 1; $\pm I_{G1\text{-}SS}$ = 10 mA; $V_{G2\text{-}S} = V_{DS} = 0$	$\pm V_{(BR)G1\text{-}SS}$		6 to 20 V
gate 2; $\pm I_{G2\text{-}SS}$ = 10 mA; $V_{G1\text{-}S} = V_{DS} = 0$	$\pm V_{(BR)G2\text{-}SS}$		6 to 20 V
Gate-source cut-off voltages			
gate 1; I_D = 20 μA; V_{DS} = 15 V; + $V_{G2\text{-}S}$ = 4 V	$-V_{(P)G1\text{-}S}$	<	2,5 V
gate 2; I_D = 20 μA; V_{DS} = 15 V; $V_{G1\text{-}S}$ = 0	$-V_{(P)G2\text{-}S}$	<	2,0 V
Drain-source cut-off voltage V_{DS} = 15 V; $V_{G2\text{-}S}$ = 4 V	I_{DSS}		2 to 20 mA

DYNAMIC CHARACTERISTICS

Measuring conditions (common source): I_D = 10 mA; V_{DS} = 15 V; + $V_{G2\text{-}S}$ = 4 V; T_{amb} = 25 °C

Transfer admittance at f = 1 kHz	$\lvert y_{fs} \rvert$	>	15 mS
		typ.	17 mS
Input capacitance at gate 1; f = 1 MHz	$C_{ig1\text{-}s}$	typ.	2,2 pF
Input capacitance at gate 2; f = 1 MHz	$C_{ig2\text{-}s}$	typ.	1,1 pF
Feedback capacitance at f = 1 MHz	C_{rs}	typ.	25 fF
Output capacitance at f = 1 MHz	C_{os}	typ.	0,8 pF
Noise figure			
at G_S = 2 mS, f = 200 MHz	F	typ.	1,5 dB
at G_S = 2 mS, f = 800 MHz	F	typ.	2,8 dB
		<	3,9 dB
Power gain			
G_S = 2 mS, G_L = 0,5 mS, f = 200 MHz	G_p	typ.	25 dB
G_S = 2 mS, G_L = 1,0 mS, f = 800 MHz	G_p	typ.	18 dB

SILICON N-CHANNEL DUAL GATE MOS-FET

Depletion type field-effect transistor in a plastic microminiature envelope (SOT-143) with source and substrate interconnected and intended for u.h.f. applications in television tuners, using SMD* technology. The device is also suitable for use in professional communication equipment.

This MOS-FET tetrode is protected against excessive input voltage surges by integrated back-to-back diodes between gates and source.

* Surface Mounted Devices

QUICK REFERENCE DATA

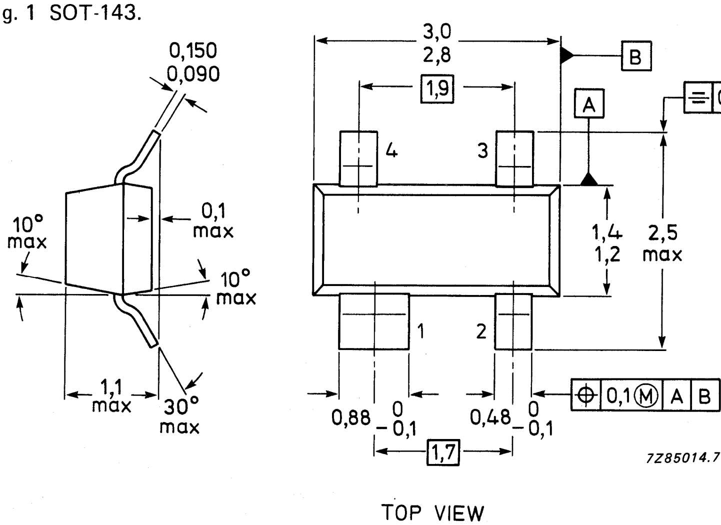
Drain-source voltage	V_{DS}	max.	20	V
Drain current	I_D	max.	30	mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300	mW
Junction temperature	T_j	max.	150	°C
Transfer admittance at f = 1 kHz I_D = 10 mA; V_{DS} = 15 V; $+V_{G2-S}$ = 4 V	$\lvert y_{fs} \rvert$	typ.	18	mS
Feedback capacitance at f = 1 MHz I_D = 10 mA; V_{DS} = 15 V; $+V_{G2-S}$ = 4 V	C_{rs}	typ.	25	fF
Noise figure at G_S = 3,3 mS I_D = 10 mA; V_{DS} = 15 V; $+V_{G2-S}$ = 4 V; f = 800 MHz	F	typ.	1,8	dB

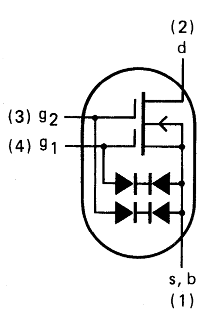
MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-143.

Marking code
BF996S = M95





RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	V_{DS}	max.	20 V
Drain current (d.c. or average)	I_D	max.	30 mA
Gate 1 - source current	$\pm I_{G1\text{-}S}$	max.	10 mA
Gate 2 - source current	$\pm I_{G2\text{-}S}$	max.	10 mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300 mW
Storage temperature	T_{stg}		−65 to 150 °C
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE

From junction to ambient in free air mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm	$R_{th\ j\text{-}a}$	=	430 K/W

STATIC CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Gate cut-off currents			
$\pm V_{G1\text{-}S}$ = 5 V; $V_{G2\text{-}S} = V_{DS}$ = 0	$\pm I_{G1\text{-}S}$	<	50 nA
$\pm V_{G2\text{-}S}$ = 5 V; $V_{G1\text{-}S} = V_{DS}$ = 0	$\pm I_{G2\text{-}S}$	<	50 nA
Gate-source breakdown voltages			
$\pm I_{G1\text{-}S}$ = 10 mA; $V_{G2\text{-}S} = V_{DS}$ = 0	$\pm V_{(BR)G1\text{-}SS}$		6,0 to 20 V
$\pm I_{G2\text{-}S}$ = 10 mA; $V_{G1\text{-}S} = V_{DS}$ = 0	$\pm V_{(BR)G2\text{-}SS}$		6,0 to 20 V
Drain current			
V_{DS} = 15 V; $V_{G1\text{-}S}$ = 0; $V_{G2\text{-}S}$ = 4 V	I_{DSS}		4 to 20 mA
Gate-source cut-off voltages			
I_D = 20 μA; V_{DS} = 15 V; $+V_{G2\text{-}S}$ = 4 V	$-V_{(P)G1\text{-}S}$	<	2,5 V
I_D = 20 μA; V_{DS} = 15 V; $V_{G1\text{-}S}$ = 0	$-V_{(P)G2\text{-}S}$	<	2,0 V

DYNAMIC CHARACTERISTICS

Measuring conditions (common source): I_D = 10 mA; V_{DS} = 15 V; $+V_{G2\text{-}S}$ = 4 V; T_{amb} = 25 °C.

Transfer admittance at f = 1 kHz	$\lvert y_{fs}\rvert$	>	15 mS
		typ.	18 mS
Input capacitance at gate 1: f = 1 MHz	$C_{ig1\text{-}s}$	typ.	2,3 pF
		<	2,6 pF
Input capacitance at gate 2: f = 1 MHz	$C_{ig2\text{-}s}$	typ.	1,2 pF
Feedback capacitance at f = 1 MHz	C_{rs}	typ.	25 fF
Output capacitance at f = 1 MHz	C_{os}	typ.	0,8 pF
Noise figure			
f = 200 MHz; G_S = 2 mS	F	typ.	1,0 dB
f = 800 MHz; G_S = 3,3 mS		typ.	1,8 dB
Power gain			
f = 200 MHz; G_S = 2 mS; G_L = 0,5 mS	G_p	typ.	25 dB
f = 800 MHz; G_S = 3,3 mS; G_L = 1,0 mS		typ.	18 dB

SILICON N-CHANNEL DUAL GATE MOS-FET

Depletion type field-effect transistor in a plastic microminiature envelope with source and substrate interconnected, intended for u.h.f. and v.h.f. applications, such as u.h.f./v.h.f. television tuners and professional communication equipment.

This MOS-FET tetrode is protected against excessive input voltage surges by integrated back-to-back diodes between gates and source and has an integrated drain resistance to suppress oscillation in the frequency range higher than 1 GHz.

This device is especially intended for use in pre-amplifiers in CATV tuners with a great tuning range up to 500 MHz.

QUICK REFERENCE DATA

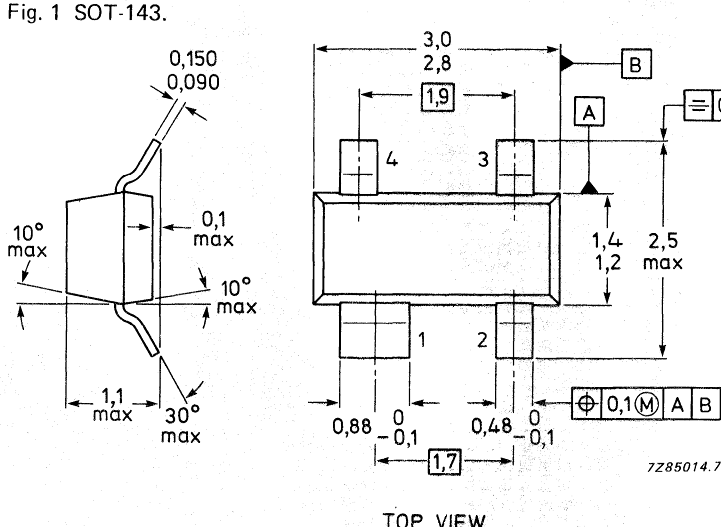
Drain-source voltage	V_{DS}	max.	20	V
Drain current (average)	$I_{D(AV)}$	max.	30	mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300	mW
Junction temperature	T_j	max.	150	°C
Transfer admittance at f = 1 kHz I_D = 10 mA; V_{DS} = 15 V; + $V_{G2\text{-}S}$ = 4 V	$\lvert y_{fs}\rvert$	typ.	18	mS
Feedback capacitance at f = 1 MHz I_D = 10 mA; V_{DS} = 15 V; + $V_{G2\text{-}S}$ = 4 V	C_{rs}	typ.	25	fF
Noise figure at G_S = 2 mS I_D = 10 mA; V_{DS} = 15 V; + $V_{G2\text{-}S}$ = 4 V; f = 200 MHz	F	typ.	1,0	dB

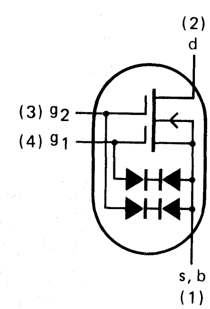
MECHANICAL DATA

Dimensions in mm

Marking code: M83

Fig. 1 SOT-143.





RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	V_{DS}	max.	20	V
Drain current (average)	$I_{D(AV)}$	max.	30	mA
Gate 1 source current	$\pm I_{G1\text{-}S}$	max.	10	mA
Gate 2 source current	$\pm I_{G2\text{-}S}$	max.	10	mA
Total power dissipation up to T_{amb} = 25 °C*	P_{tot}	max.	300	mW
Storage temperature	T_{stg}	−65 to + 150		°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE

From junction to ambient in free air*	$R_{th\ j\text{-}a}$	=	430	K/W

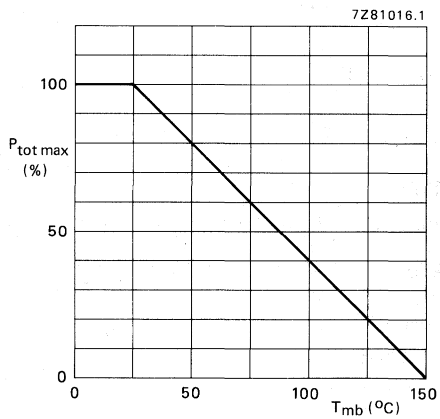


Fig. 2 Power derating curve.

* Device mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

STATIC CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Gate cut-off currents			
gate 1; $\pm V_{G1\text{-}S}$ = 5 V; $V_{G2\text{-}S} = V_{DS}$ = 0	$\pm I_{G1\text{-}SS}$	<	50 nA
gate 2; $\pm V_{G2\text{-}S}$ = 5 V; $V_{G1\text{-}S} = V_{DS}$ = 0	$\pm I_{G2\text{-}SS}$	<	50 nA
Gate-source breakdown voltages			
gate 1; $\pm I_{G1\text{-}SS}$ = 10 mA; $V_{G2\text{-}S} = V_{DS}$ = 0	$\pm V_{(BR)G1\text{-}SS}$		6 to 20 V
gate 2; $\pm I_{G2\text{-}SS}$ = 10 mA; $V_{G1\text{-}S} = V_{DS}$ = 0	$\pm V_{(BR)G2\text{-}SS}$		6 to 20 V
Gate-source cut-off voltages			
gate 1; I_D = 20 μA; V_{DS} = 15 V; + $V_{G2\text{-}S}$ = 4 V	$-V_{(P)G1\text{-}S}$	<	2,5 V
gate 2; I_D = 20 μA; V_{DS} = 15 V; $V_{G1\text{-}S}$ = 0	$-V_{(P)G2\text{-}S}$	<	2,0 V
Drain-source cut-off voltage V_{DS} = 15 V; $V_{G2\text{-}S}$ = 4 V; $V_{G1\text{-}S}$ = 0	I_{DSS}		2 to 20 mA

DYNAMIC CHARACTERISTICS

Measuring conditions (common source): I_D = 10 mA; V_{DS} = 15 V; + $V_{G2\text{-}S}$ = 4 V; T_{amb} = 25 °C

Transfer admittance at f = 1 kHz	$\|y_{fs}\|$	>	15 mS
		typ.	18 mS
Input capacitance at gate 1; f = 1 MHz	$C_{ig1\text{-}s}$	typ.	2,5 pF
Input capacitance at gate 2; f = 1 MHz	$C_{ig2\text{-}s}$	typ.	1,2 pF
Feedback capacitance at f = 1 MHz	C_{rs}	typ.	25 fF
Output capacitance at f = 1 MHz	C_{os}	typ.	1,0 pF
Noise figure at f = 200 MHz; G_S = 2 mS	F	typ.	1,0 dB
Power gain at G_S = 2 mS, G_L = 0,5 mS, f = 200 MHz	G_p	typ.	25 dB

DEVELOPMENT DATA

N-P-N 2 GHz WIDEBAND TRANSISTOR

N-P-N transistor in a four-lead dual-emitter plastic envelope (SOT-143). It is designed for wideband application in the GHz range, such as satellite TV systems (SATV) and repeater amplifiers in fibre-optical systems. The device features a very high transition frequency, high gain and a very low noise figure up to high frequencies.

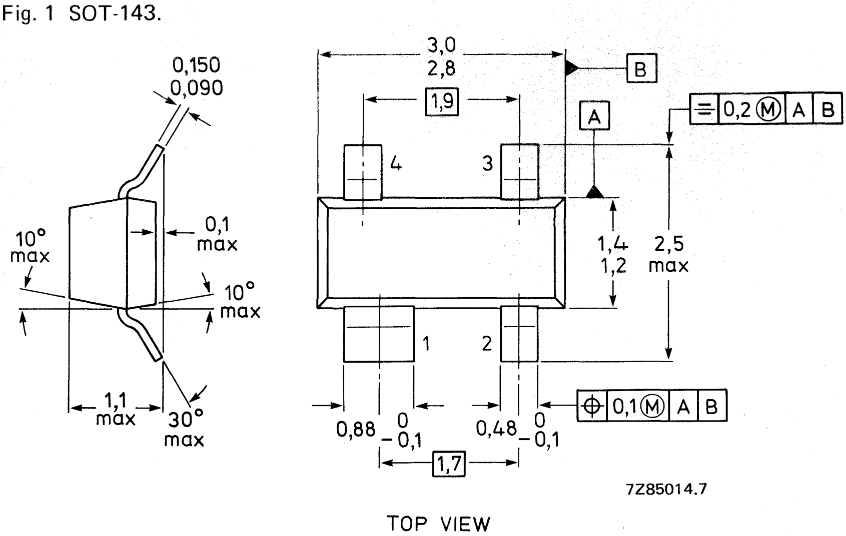
QUICK REFERENCE DATA

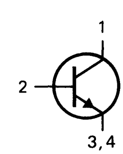
Collector-base voltage	V_{CBO}	max.	20	V
Collector-emitter voltage	V_{CEO}	max.	10	V
Collector current (d.c.)	I_C	max.	50	mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300	mW
Junction temperature	T_j	max.	150	°C
D.C. current gain I_C = 15 mA; V_{CE} = 5 V	h_{FE}	min.	60	
		typ.	100	
Transition frequency at f = 500 MHz I_C = 15 mA; V_{CE} = 8 V	f_T	typ.	7,5	GHz
Maximum unilateral power gain at f = 2 GHz I_C = 15 mA; V_{CE} = 8 V; T_{amb} = 25 °C	G_{UM}	typ.	10,0	dB
Noise figure at f = 2 GHz Z_S = 60 Ω; T_{amb} = 25 °C				
I_C = 5 mA; V_{CE} = 8 V	F	typ.	2,5	dB
I_C = 15 mA; V_{CE} = 8 V	F	typ.	3,0	dB

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-143.





RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	V_{CBO}	max.	20 V
Collector-emitter voltage (open base)	V_{CEO}	max.	10 V
Emitter-base voltage (open collector)	V_{EBO}	max.	2,5 V
Collector current (d.c.)	I_C	max.	50 mA
Total power dissipation up to T_{amb} = 25 °C mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm	P_{tot}	max.	300 mW
Storage temperature	T_{stg}	−65 to + 150 °C	
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE

From junction to ambient mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm	$R_{th\ j\text{-}a}$	=	430 K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current $I_E = 0$; V_{CB} = 10 V	I_{CBO}	max.	50 nA
D.C. current gain I_C = 15 mA; V_{CE} = 5 V	h_{FE}	min.	60
		typ.	100
Transition frequency at f = 500 MHz I_C = 15 mA; V_{CE} = 8 V	f_T	typ.	7,5 GHz
Collector capacitance at f = 1 MHz $I_E = I_e = 0$; V_{CB} = 8 V	C_c	typ.	0,7 pF
Emitter capacitance at f = 1 MHz $I_C = I_c = 0$; V_{EB} = 0,5 V	C_e	typ.	1,3 pF
Feedback capacitance at f = 1 MHz $I_C = 0$; V_{CE} = 8 V	C_{re}	typ.	0,5 pF

Maximum unilateral power gain (s_{re} assumed to be zero)

$$G_{UM} = 10 \log \frac{|s_{fe}|^2}{[1-|s_{ie}|^2]\,[1-|s_{oe}|^2]}$$

at I_C = 15 mA; V_{CE} = 8 V; f = 2 GHz; T_{amb} = 25 °C	G_{UM}	typ.	10,0 dB
Noise figures at f = 800 MHz; Z_S = opt.; T_{amb} = 25 °C; V_{CE} = 8 V			
I_C = 5 mA	F	typ.	0,8 dB
I_C = 15 mA	F	typ.	1,5 dB
Noise figures at f = 2 GHz; Z_S = 60 Ω; T_{amb} = 25 °C; V_{CE} = 8 V			
I_C = 5 mA	F	typ.	2,5 dB
I_C = 15 mA	F	typ.	3,0 dB

s-parameters (common emitter) at V_{CE} = 8 V; T_{amb} = 25 °C; typical values.

I_C mA	f MHz	s_{ie}	s_{fe}	s_{re}	s_{oe}	G_{UM} dB
	40	0,96/ −6,8°	5,8/177,8°	0,01/ 84,5°	0,99/ −3,2°	44,1
	100	0,98/ −20,8°	5,6/165,8°	0,03/ 77,5°	1,01/ −10,0°	46,5
	200	0,89/ −40,1°	5,1/153,2°	0,05/ 66,8°	0,91/ −19,0°	28,7
	500	0,81/ −89,3°	4,3/121,5°	0,09/ 43,4°	0,79/ −38,5°	21,5
2	800	0,68/−123,0°	3,3/102,0°	0,11/ 33,8°	0,67/ −50,0°	15,7
	1000	0,64/−139,9°	2,8/ 89,8°	0,11/ 28,0°	0,65/ −54,5°	13,7
	1200	0,60/−157,3°	2,3/ 81,1°	0,11/ 25,8°	0,62/ −61,7°	11,5
	1500	0,59/−173,3°	2,0/ 71,8°	0,11/ 27,4°	0,55/ −69,3°	9,5
	2000	0,57/+161,7°	1,5/ 56,3°	0,10/ 32,2°	0,54/ −85,8°	6,7
	40	0,91/ −10,9°	13,5/174,8°	0,01/ 83,3°	0,98/ −5,9°	44,2
	100	0,91/ −30,3°	12,6/159,5°	0,03/ 72,2°	0,96/ −17,0°	40,9
	200	0,79/ −56,3°	10,6/143,5°	0,04/ 60,3°	0,81/ −29,5°	29,3
	500	0,64/−115,9°	7,4/109,8°	0,07/ 41,4°	0,58/ −50,8°	21,5
5	800	0,55/−145,5°	5,2/ 93,5°	0,08/ 39,9°	0,48/ −59,5°	17,1
	1000	0,53/−161,4°	4,2/ 84,0°	0,08/ 39,1°	0,44/ −62,2°	15,0
	1200	0,52/−176,5°	3,5/ 77,8°	0,08/ 41,2°	0,42/ −67,1°	13,1
	1500	0,51/+172,2°	2,9/ 69,1°	0,09/ 44,6°	0,38/ −75,7°	11,3
	2000	0,50/+149,8°	2,2/ 56,7°	0,11/ 49,8°	0,38/ −89,5°	8,7
	40	0,85/ −16,1°	23,5/170,6°	0,01/ 80,1°	0,96/ −9,7°	43,8
	100	0,81/ −42,6°	21,3/151,8°	0,02/ 67,2°	0,89/ −25,2°	38,0
	200	0,67/ −76,3°	16,6/133,0°	0,04/ 55,5°	0,68/ −40,0°	29,6
	500	0,54/−137,5°	9,5/101,5°	0,05/ 45,7°	0,42/ −60,2°	21,9
10	800	0,49/−161,8°	6,3/ 88,5°	0,07/ 49,2°	0,35/ −67,0°	17,7
	1000	0,49/−175,2°	5,1/ 80,5°	0,07/ 50,6°	0,32/ −68,9°	15,8
	1200	0,49/+171,5°	4,2/ 75,8°	0,08/ 53,4°	0,29/ −72,5°	13,9
	1500	0,47/+163,5°	3,5/ 67,5°	0,09/ 55,3°	0,28/ −82,1°	12,3
	2000	0,47/+142,5°	2,6/ 56,8°	0,12/ 57,7°	0,29/ −94,5°	9,6
	40	0,80/ −20,1°	31,0/167,8°	0,01/ 76,4°	0,94/ −12,2°	43,5
	100	0,74/ −51,8°	26,9/146,8°	0,02/ 64,1°	0,83/ −30,3°	37,2
	200	0,60/ −89,4°	19,9/126,7°	0,03/ 54,0°	0,60/ −45,5°	29,8
	500	0,51/−147,5°	10,3/ 98,0°	0,05/ 49,7°	0,35/ −64,9°	22,1
15	800	0,47/−168,5°	6,7/ 86,5°	0,06/ 54,6°	0,29/ −70,8°	18,1
	1000	0,47/+179,2°	5,4/ 79,3°	0,07/ 55,9°	0,27/ −72,8°	16,1
	1200	0,48/+166,5°	4,4/ 75,0°	0,08/ 58,4°	0,24/ −75,8°	14,3
	1500	0,46/+160,0°	3,7/ 67,0°	0,10/ 59,2°	0,24/ −86,0°	12,5
	2000	0,45/+139,5°	2,7/ 56,8°	0,12/ 60,2°	0,25/ −97,8°	10,0
	40	0,76/ −23,8°	37,2/165,4°	0,01/ 75,6°	0,92/ −14,3°	43,3
	100	0,69/ −60,0°	31,2/142,6°	0,02/ 61,7°	0,78/ −34,3°	36,8
	200	0,55/ −99,6°	21,8/122,5°	0,03/ 53,6°	0,54/ −49,5°	29,8
	500	0,49/−152,5°	10,6/ 96,0°	0,04/ 53,0°	0,31/ −68,0°	22,2
20	800	0,46/−172,9°	7,0/ 85,0°	0,06/ 58,1°	0,26/ −73,3°	18,2
	1000	0,46/+175,9°	5,5/ 78,3°	0,07/ 59,3°	0,24/ −75,3°	16,1
	1200	0,47/+163,5°	4,6/ 74,3°	0,08/ 61,5°	0,21/ −78,3°	14,5
	1500	0,45/+157,9°	3,8/ 66,4°	0,10/ 61,4°	0,22/ −88,9°	12,8
	2000	0,45/+137,8°	2,8/ 56,7°	0,12/ 61,7°	0,22/−100,2°	10,2

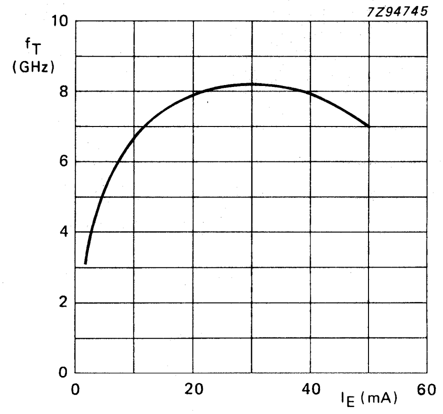


Fig. 2 V_{CE} = 8 V; f = 500 MHz;
T_{amb} = 25 °C; typical values.

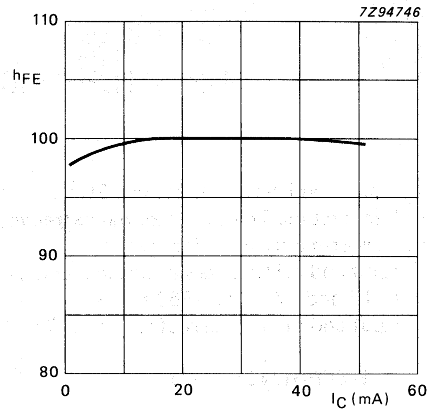


Fig. 3 V_{CE} = 5 V; T_{amb} = 25 °C;
typical values.

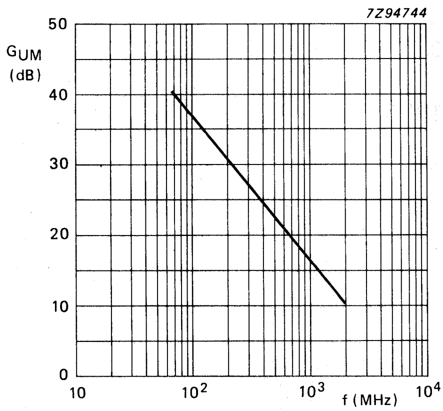


Fig. 4 V_{CE} = 8 V; I_C = 15 mA;
T_{amb} = 25 °C; typical values.

N-P-N H.F. WIDEBAND TRANSISTOR

N-P-N multi-emitter transistor in a SOT-89 plastic envelope intended for application in thick and thin-film circuits. The transistor has extremely good intermodulation properties and a high power gain. It is primarily intended for:

- Output and driver stages of channel and band serial amplifiers with high output power for bands I, II, III and IV/V (40–860 MHz).
- Output and driver stages of wideband amplifiers.

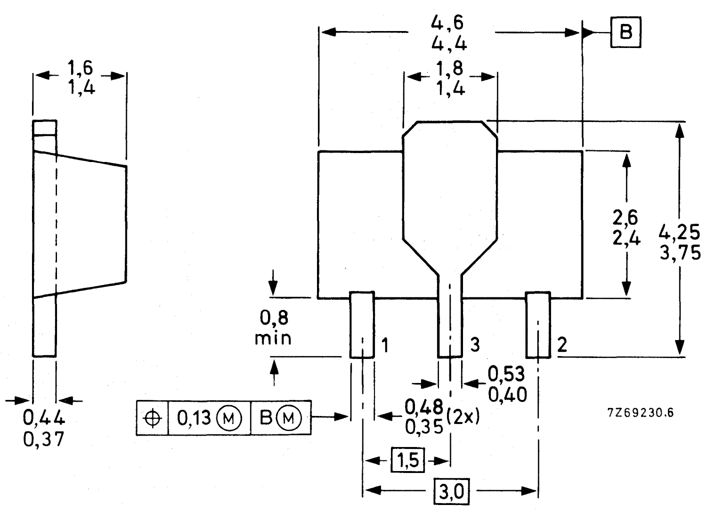
QUICK REFERENCE DATA

Collector-base voltage (open emitter; peak value)	V_{CBOM}	max.	40	V
Collector-emitter voltage (open base)	V_{CEO}	max.	25	V
Collector current (peak value; f > 1 MHz)	I_{CM}	max.	300	mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	1	W
Junction temperature	T_j	max.	150	°C
Transition frequency at f = 500 MHz I_C = 150 mA; V_{CE} = 15 V	f_T	typ.	1,2	GHz
Feedback capacitance at f = 1 MHz I_C = 10 mA; V_{CE} = 15 V;	C_{re}	typ.	1,9	pF

MECHANICAL DATA

Dimensions in mm

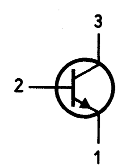
Fig. 1 SOT-89.



BOTTOM VIEW

Mark

BFQ17 = FA



See also *Soldering recommendations*.

RATINGS Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter; peak value)	V_{CBOM}	max.	40	V	
Collector-emitter voltage (R_{BE} ≤ 50 Ω; peak value)	V_{CERM}	max.	40	V	[1]
Collector-emitter voltage (open base)	V_{CEO}	max.	25	V	[1]
Emitter-base voltage (open collector)	V_{EBO}	max.	2	V	
Collector current (d.c.)	I_C	max.	150	mA	
Collector current (peak value; f > 1 MHz)	I_{CM}	max.	300	mA	
Total power dissipation up to T_{amb} = 25 °C mounted on a ceramic substrate area = 2,5 cm^2; thickness = 0,7 mm	P_{tot}	max.	1	W	
Storage temperature	T_{stg}		−65 to +150	°C	
Junction temperature	T_j	max.	150	°C	

THERMAL RESISTANCE

From junction to collector tab	$R_{th\,j-tab}$	=	30	K/W
From junction to ambient in free air mounted on a ceramic substrate area = 2,5 cm^2; thickness = 0,7 mm	$R_{th\,j-a}$	=	125	K/W

[1]) I_C = 10 mA.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current				
$I_E = 0$; $V_{CB} = 20$ V; $T_j = 150$ °C	I_{CBO}	max.	20	μA
Saturation voltage				
$I_C = 100$ mA; $I_B = 10$ mA	V_{CEsat}	max.	0,5	V
D.C. current gain				
$I_C = 50$ mA; $V_{CE} = 5$ V	h_{FE}	min.	25	
$I_C = 150$ mA; $V_{CE} = 5$ V	h_{FE}	min.	25	
Transition frequency at f = 500 MHz [1]				
$I_C = 150$ mA; $V_{CE} = 15$ V	f_T	typ.	1,2	GHz
Collector capacitance at f = 1 MHz				
$I_E = I_e = 0$; $V_{CB} = 15$ V	C_c	max.	4	pF
Feedback capacitance at f = 1 MHz				
$I_C = 10$ mA; $V_{CE} = 15$ V; $T_{amb} = 25$ °C	C_{re}	typ.	1,9	pF

Max. unilateral power gain (s_{re} assumed to be zero)

$$G_{UM} = 10 \log \frac{|s_{fe}|^2}{(1 - |s_{ie}|^2)(1 - |s_{oe}|^2)}$$

$I_C = 60$ mA; $V_{CE} = 15$ V; $T_{amb} = 25$ °C;				
f = 200 MHz	G_{UM}	typ.	16	dB
f = 800 MHz	G_{UM}	typ.	6,5	dB

1) Measured under pulse conditions.

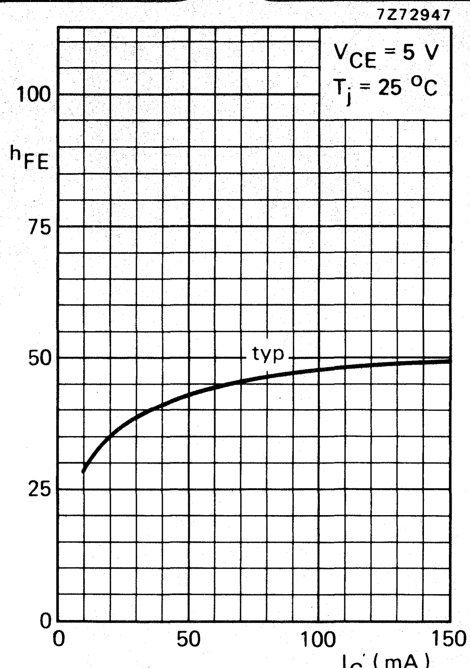


Fig. 2. V_{CE} = 5V; T_j = 25 °C; typical values

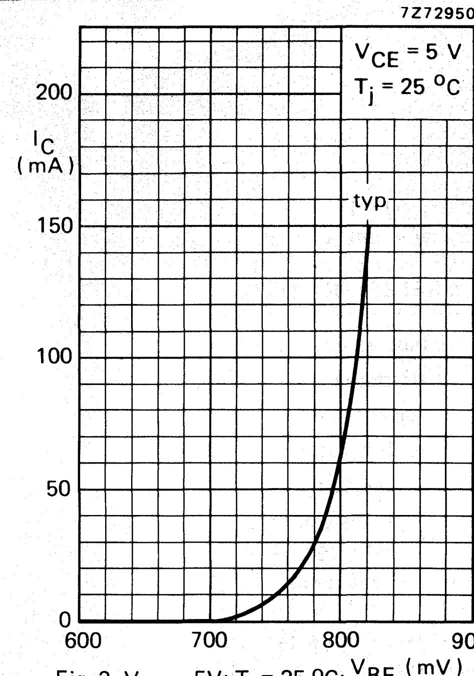


Fig. 3. V_{CE} = 5V; T_j = 25 °C; typical values

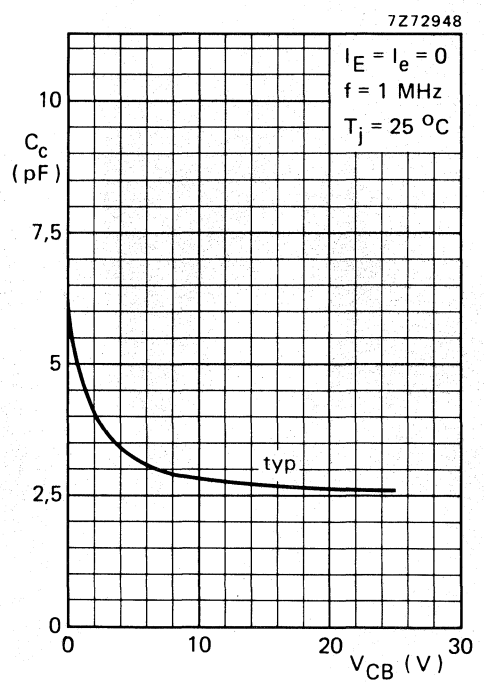


Fig. 4. $I_E = i_e = 0$; f = 1 MHz; T_j = 25 °C; typical values

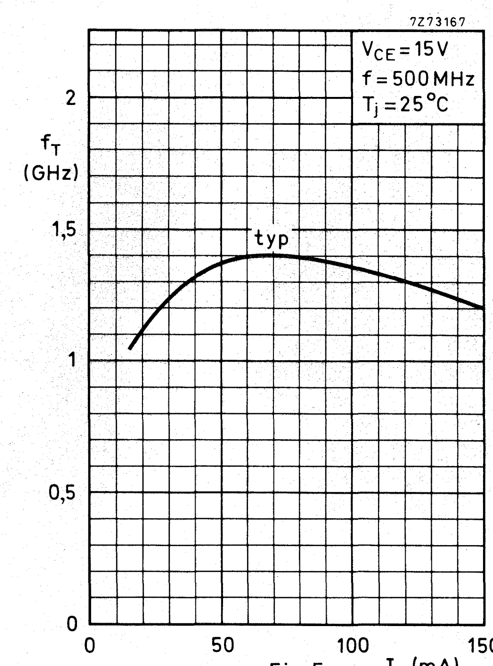


Fig. 5. V_{CE} = 15V; f = 500 MHz; T_j = 25 °C; typical values

N-P-N H.F. WIDEBAND TRANSISTOR

N-P-N transistor in a plastic SOT-89 envelope intended for application in thick and thin-film circuits. It is primarily intended for MATV purposes.

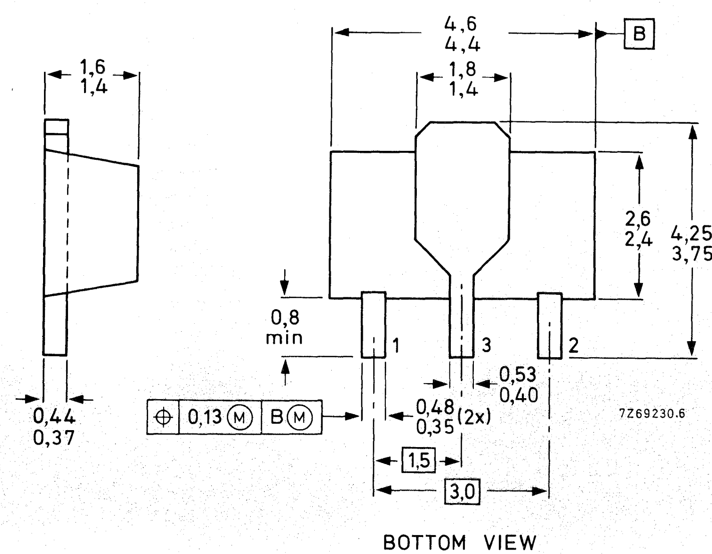
QUICK REFERENCE DATA

Collector-base voltage (open emitter)	V_{CBO}	max.	25	V
Collector-emitter voltage (open base)	V_{CEO}	max.	15	V
Collector current (d.c.)	I_C	max.	150	mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	1	W
Junction temperature	T_j	max.	150	°C
Transition frequency at f = 500 MHz I_C = 100 mA; V_{CE} = 10 V	f_T	typ.	3,6	GHz
Feedback capacitance at f = 10,7 MHz I_C = 0; V_{CE} = 10 V	C_{re}	typ.	1,2	pF
Intermodulation distortion I_C = 80 mA; V_{CE} = 10 V; R_L = 75 Ω measured at $f_{(p+q-r)}$ = 793,25 MHz	d_{im}	max.	−60	dB

MECHANICAL DATA

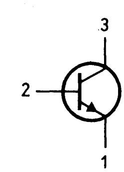
Dimensions in mm

Fig. 1 SOT-89.



Mark

BFQ18A = FF



See also soldering recommendations

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	V_{CBO}	max.	25	V
Collector-emitter voltage (open base)	V_{CEO}	max.	15	V
Emitter-base voltage (open collector)	V_{EBO}	max.	2	V
Collector current (d.c.)	I_C	max.	150	mA
Total power dissipation up to T_{amb} = 25 °C *	P_{tot}	max.	1	W
Storage temperature	T_{stg}	−65 to + 150		°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE

From junction to collector tab	$R_{th\ j\text{-}tab}$	=	25	K/W
From junction to ambient in free air *	$R_{th\ j\text{-}a}$	=	125	K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

D.C. current gain **				
I_C = 50 mA; V_{CE} = 10 V	h_{FE}	min.	25	
I_C = 100 mA; V_{CE} = 10 V	h_{FE}	min.	25	
Transition frequency at f = 500 MHz **				
I_C = 50 mA; V_{CE} = 10 V	f_T	typ.	3,2	GHz
I_C = 100 mA; V_{CE} = 10 V	f_T	typ.	3,6	GHz
Collector capacitance at f = 1 MHz				
$I_E = I_e = 0$; V_{CB} = 10 V	C_c	typ.	2,0	pF
Emitter capacitance at f = 1 MHz				
$I_C = I_c = 0$; V_{EB} = 0,5 V	C_e	typ.	11	pF
Feedback capacitance at f = 10,7 MHz				
$I_C = 0$; V_{CE} = 10 V	C_{re}	typ.	1,2	pF

* The device mounted on a ceramic substrate area = 2,5 cm^2; thickness = 0,7 mm.
** Measured under pulse conditions.

Intermodulation distortion (see Fig. 2)

I_C = 80 mA; V_{CE} = 10 V; R_L = 75 Ω
$V_p = V_o$ = 700 mV at f_p = 795,25 MHz
$V_q = V_o$ −6 dB at f_q = 803,25 MHz
$V_r = V_o$ −6 dB at f_r = 805,25 MHz
Measured at $f_{(p+q-r)}$ = 793,25 MHz — d_{im} max. −60 dB

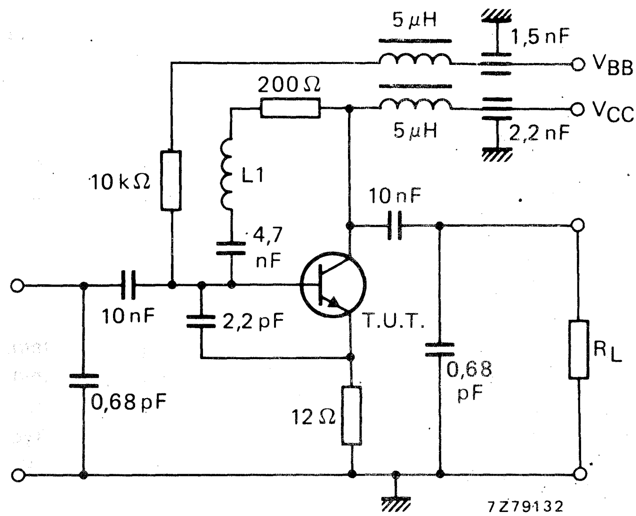


Fig. 2 MATV-test circuit (40–860 MHz).

N-P-N 1 GHz WIDEBAND TRANSISTOR

N-P-N transistor in a SOT-89 plastic envelope intended for application in thick- and thin-film circuits.
It is primarily intended for use in u.h.f. and microwave amplifiers such as in aerial amplifiers, radar systems, oscilloscopes, spectrum analysers etc.
The transistor features very low intermodulation distortion and high power gain. Thanks to its very high transition frequency, it also has excellent wideband properties and low noise up to high frequencies.

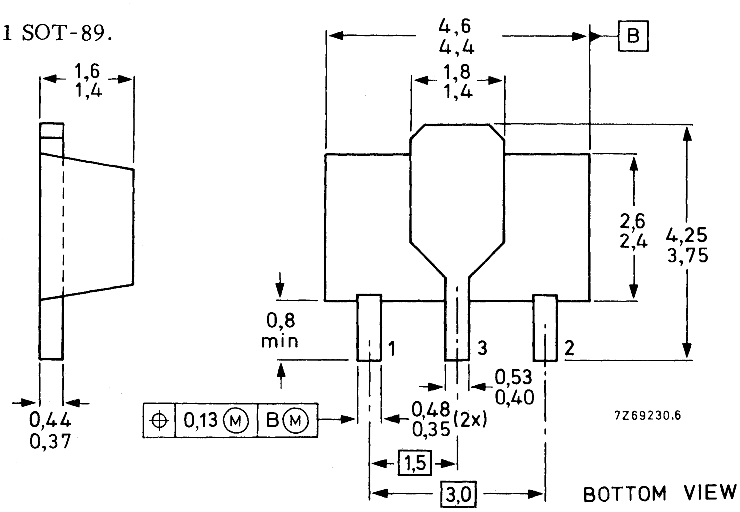
QUICK REFERENCE DATA

Collector-base voltage (open emitter)	V_{CBO}	max.	20	V
Collector-emitter voltage (open base)	V_{CEO}	max.	15	V
Collector current (d.c.)	I_C	max.	75	mA
Total power dissipation up to T_{amb} = 87,5 °C	P_{tot}	max.	500	mW
Junction temperature	T_j	max.	150	°C
Transition frequency at f = 500 MHz I_C = 50 mA; V_{CE} = 10 V	f_T	typ.	5	GHz
Feedback capacitance at f = 1 MHz I_C = 10 mA; V_{CE} = 10 V;	C_{re}	typ.	1,3	pF
Noise figure at optimum source impedance I_C = 50 mA; V_{CE} = 10 V; f = 500 MHz;	F	typ.	3,3	dB

MECHANICAL DATA

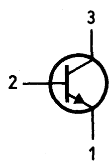
Dimensions in mm

Fig. 1 SOT-89.



Mark

BFQ19 = FB



See also soldering recommendations

RATINGS Limiting values in accordance with the Absolute Maximum System (IEC134)

Collector-base voltage (open emitter)	V_{CBO}	max.	20	V
Collector-emitter voltage (open base)	V_{CEO}	max.	15	V
Emitter-base voltage (open collector)	V_{EBO}	max.	3,3	V
Collector current (d.c.)	I_C	max.	75	mA
Collector current (peak value); f > 1 MHz	I_{CM}	max.	150	mA
Total power dissipation up to T_{amb} = 87,5 °C mounted on a ceramic substrate area = 2,5 cm^2; thickness = 0,7 mm	P_{tot}	max.	500	mW
Storage temperature	T_{stg}		−65 to +150	°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE

From junction to collector tab	$R_{th\,j-tab}$	=	40	K/W
From junction to ambient in free air mounted on a ceramic substrate area = 2,5 cm^2; thickness = 0,7 mm	$R_{th\,j-a}$	=	125	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current				
$I_E = 0$: $V_{CB} = 10$ V	I_{CBO}	max.	100	nA
D.C. current gain [1]				
$I_C = 50$ mA; $V_{CE} = 10$ V	h_{FE}	min.	25	
		typ.	50	
$I_C = 75$ mA; $V_{CE} = 10$ V	h_{FE}	min.	25	
		typ.	52	
Transition frequency at f = 500 MHz [1]				
$I_C = 50$ mA; $V_{CE} = 10$ V	f_T	min.	4,0	GHz
		typ.	5,0	GHz
$I_C = 75$ mA; $V_{CE} = 10$ V	f_T	min.	4,4	GHz
		typ.	5,5	GHz
Collector capacitance at f = 1 MHz				
$I_E = I_e = 0$: $V_{CB} = 10$ V	C_c	typ.	1,6	pF
Emitter capacitance at f = 1 MHz				
$I_C = I_c = 0$: $V_{EB} = 0,5$ V	C_e	typ.	5,0	pF
Feedback capacitance at f = 1 MHz				
$I_C = 10$ mA; $V_{CE} = 10$ V; $T_{amb} = 25$ °C	C_{re}	typ.	1,3	pF
Noise figure at optimum source impedance				
$I_C = 50$ mA; $V_{CE} = 10$ V; f = 500 MHz; $T_{amb} = 25$ °C	F	typ.	3,3	dB

Max. unilateral power gain (s_{re} assumed to be zero)

$$G_{UM} = 10 \log \frac{|s_{fe}|^2}{(1 - |s_{ie}|^2)(1 - |s_{oe}|^2)}$$

$I_C = 50$ mA; $V_{CE} = 10$ V; $T_{amb} = 25$ °C:

f = 200 MHz	G_{UM}	typ.	18,5	dB
f = 500 MHz	G_{UM}	typ.	11,5	dB
f = 800 MHz	G_{UM}	typ.	7,5	dB

1) Measured under pulse conditions.

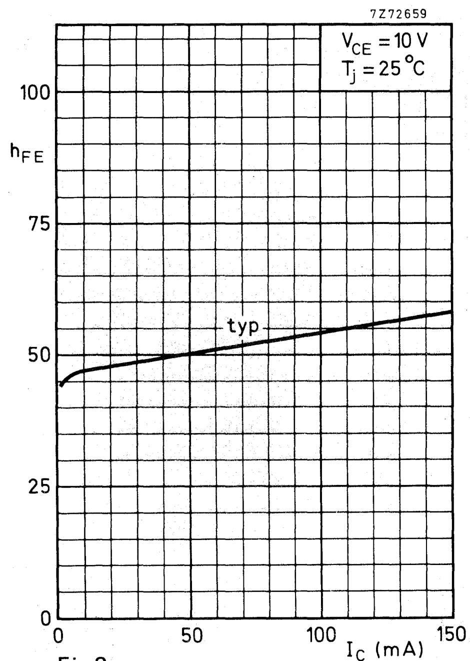


Fig.2.

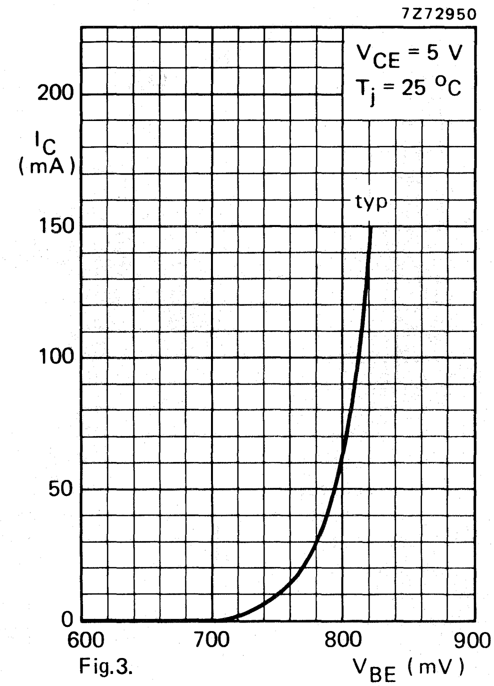


Fig.3.

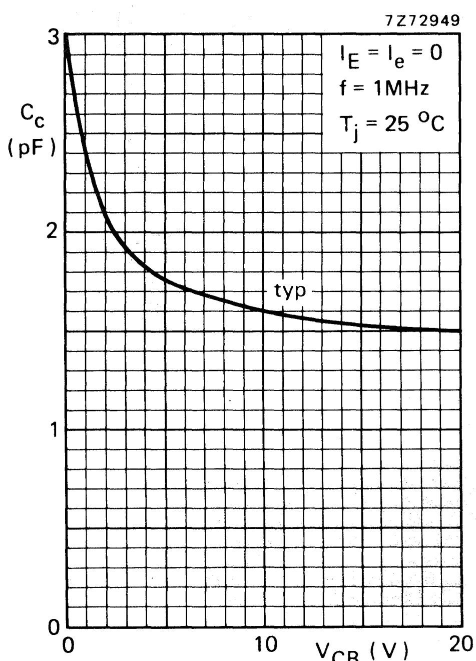


Fig.4.

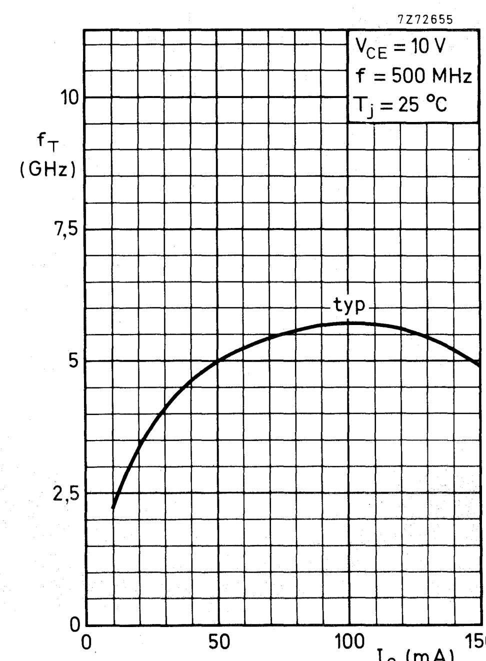


Fig.5.

N-P-N 2 GHz WIDEBAND TRANSISTOR

N-P-N transistor in a plastic SOT-23 envelope. It is designed for wideband application in the GHz range, such as satellite TV systems (SATV) and repeater amplifiers in fibre-optical systems. The device features a very high transition frequency and a very low noise figure up to high frequencies.

QUICK REFERENCE DATA

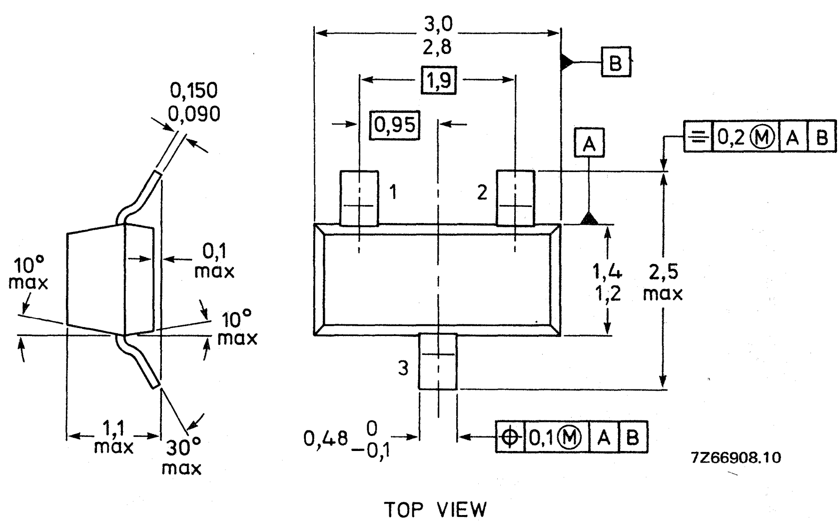
Collector-base voltage, open emitter	V_{CBO}	max.	20 V
Collector-emitter voltage, open base	V_{CEO}	max.	10 V
Collector current (d.c.)	I_C	max.	50 mA
Total power dissipation up to T_{amb} = 70 °C	P_{tot}	max.	180 mW
Junction temperature	T_j	max.	150 °C
D.C. current gain I_C = 15 mA; V_{CB} = 5 V	h_{FE}	typ.	100
Transition frequency at f = 500 MHz I_C = 15 mA; V_{CE} = 8 V	f_T	typ.	7,5 GHz
Maximum unilateral power gain at f = 2 GHz I_C = 15 mA; V_{CE} = 8 V	G_{UM}	typ.	8,0 dB

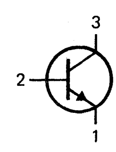
MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-23.

Mark : V2





If required, the R-version (reverse pinning) is available on request.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	V_{CBO}	max.	20	V
Collector-emitter voltage (open base)	V_{CEO}	max.	10	V
Emitter-base voltage (open collector)	V_{EBO}	max.	2,5	V
Collector current (d.c.)	I_C	max.	50	mA
Total power dissipation up to T_{amb} = 70 °C*	P_{tot}	max.	180	mW
Storage temperature	T_{stg}	−65 to + 150		°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE

From junction to ambient in free air*	$R_{th\ j\text{-}a}$	=	430	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current				
$I_E = 0$; $V_{CB} = 5$ V	I_{CBO}	max.	50	nA
D.C. current gain				
$I_C = 15$ mA; $V_{CB} = 5$ V	h_{FE}	typ.	100	
Transition frequency at f = 500 mHz				
$I_C = 15$ mA; $V_{CE} = 8$ V	f_T	typ.	7,5	GHz
Collector capacitance at f = 1 MHz				
$I_E = i_e = 0$; $V_{CB} = 8$ V	C_c	typ.	0,7	pF
Emitter capacitance at f = 1 MHz				
$I_C = i_c = 0$; $V_{EB} = 0,5$ V	C_e	typ.	1,3	pF
Feedback capacitance at f = 1 MHz				
$I_C = 0$; $V_{CE} = 8$ V	C_{re}	typ.	0,5	pF

Maximum unilateral power gain (s_{re} assumed to be zero)

$$G_{UM} = 10 \log \frac{|s_{fe}|^2}{[1-|s_{ie}|^2]\,[1-|s_{oe}|^2]}$$

$I_C = 15$ mA; $V_{CE} = 8$ V; f = 2 GHz; T_{amb} = 25 °C	G_{UM}	typ.	8,0	dB
Noise figure at f = 2 GHz; $R_S = 60\ \Omega$; T_{amb} = 25 °C				
$I_C = 5$ mA; $V_{CE} = 8$ V	F	typ.	2,5	dB
$I_C = 15$ mA; $V_{CE} = 8$ V	F	typ.	3,0	dB

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

s-parameters (common emitter) at V_{CE} = 8 V; typical values.

I_C mA	f MHz	s_{ie}	s_{fe}	s_{re}	s_{oe}	G_{UM} dB
	40	0,93/ −9,5°	7,07/174,6°	0,01/83,2°	1,00/ −4,5°	46,7
	100	0,90/ −22,8°	6,96/163,5°	0,03/76,3°	0,97/−10,4°	36,4
	200	0,84/ −42,1°	6,35/150,4°	0,06/66,4°	0,91/−17,9°	29,2
2	500	0,61/ −90,7°	4,40/117,2°	0,10/45,7°	0,67/−32,6°	17,5
	800	0,55/−118,0°	3,24/102,6°	0,12/42,2°	0,60/−38,2°	13,7
	1000	0,54/−135,5°	2,70/ 93,5°	0,12/41,2°	0,55/−43,6°	11,9
	2000	0,47/ 177,3°	1,57/ 64,5°	0,15/60,0°	0,47/−65,3°	6,1
	40	0,84/ −14,9°	15,47/170,5°	0,01/80,7°	0,99/ −7,9°	44,5
	100	0,78/ −36,1°	14,35/154,8°	0,03/71,1°	0,92/−18,0°	35,4
	200	0,68/ −63,3°	11,97/137,7°	0,05/60,6°	0,79/−29,0°	28,5
5	500	0,45/−119,8°	6,74/106,1°	0,08/49,7°	0,47/−40,1°	18,6
	800	0,42/−143,5°	4,55/ 94,7°	0,09/53,8°	0,41/−41,5°	14,8
	1000	0,43/−155,4°	3,80/ 87,4°	0,10/56,1°	0,37/−46,7°	13,1
	2000	0,35/ 169,2°	2,04/ 63,5°	0,18/69,4°	0,34/−63,3°	7,3
	40	0,74/ −22,8°	25,66/165,6°	0,01/77,5°	0,96/−12,1°	43,0
	100	0,65/ −51,2°	22,19/145,5°	0,03/66,8°	0,84/−26,3°	34,6
	200	0,53/ −85,2°	16,35/126,4°	0,04/58,1°	0,64/−38,4°	28,0
10	500	0,38/−144,4°	8,01/ 99,5°	0,06/58,0°	0,33/−42,8°	19,2
	800	0,36/−161,9°	5,29/ 90,0°	0,09/64,0°	0,30/−41,2°	15,5
	1000	0,38/ 169,9°	4,27/ 84,0°	0,10/66,0°	0,27/−47,0°	13,6
	2000	0,30/ 160,0°	2,29/ 62,8°	0,20/72,6°	0,27/−61,2°	7,9
	40	0,67/ −28,3°	32,67/162,1°	0,01/75,8°	0,94/−14,9°	42,5
	100	0,57/ −62,8°	26,66/139,6°	0,02/64,6°	0,78/−31,4°	34,2
	200	0,46/ −99,5°	18,35/120,6°	0,04/58,7°	0,56/−42,8°	27,9
15	500	0,36/−154,8°	8,49/ 96,8°	0,06/62,9°	0,27/−42,8°	19,5
	800	0,34/ 169,3°	5,55/ 88,4°	0,09/68,4°	0,26/−39,7°	15,7
	1000	0,36/ 176,8°	4,47/ 82,5°	0,10/69,7°	0,23/−46,3°	13,9
	2000	0,29/ 155,7°	2,37/ 62,3°	0,21/73,4°	0,25/−59,8°	8,2
	40	0,63/ −32,5°	37,50/159,4°	0,01/74,2°	0,93/−17,2°	42,0
	100	0,52/ −70,8°	29,23/135,5°	0,02/63,4°	0,73/−34,7°	34,0
	200	0,42/−108,8°	19,22/117,4°	0,03/59,7°	0,50/−45,0°	27,8
20	500	0,35/−162,0°	8,69/ 95,0°	0,06/64,9°	0,23/−41,6°	19,6
	800	0,33/−175,1°	5,62/ 86,9°	0,09/70,7°	0,24/−38,1°	15,7
	1000	0,36/−178,7°	4,57/ 81,7°	0,10/71,6°	0,21/−45,0°	14,0
	2000	0,28/−153,5°	2,40/ 62,0°	0,21/73,8°	0,24/−58,9°	8,2

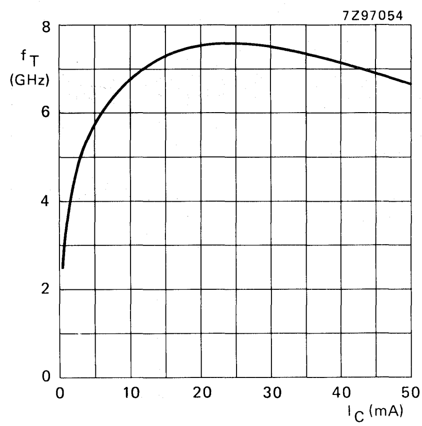


Fig. 2 V_{CE} = 8 V; f = 500 MHz; typical values.

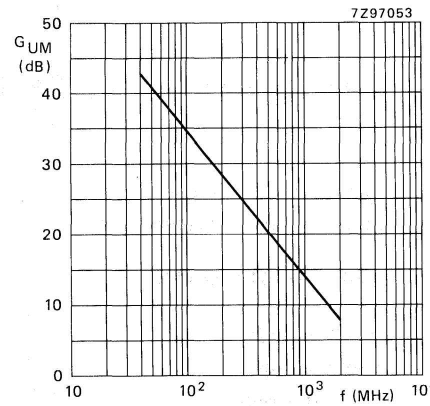


Fig. 3 V_{CE} = 8 V; I_C = 15 mA;
T_{amb} = 25 °C; typical values.

N-CHANNEL SILICON FIELD-EFFECT TRANSISTORS

Planar epitaxial junction field effect transistor in a microminiature plastic envelope. It is intended for low level general purpose amplifiers in thick and thin-film circuits.

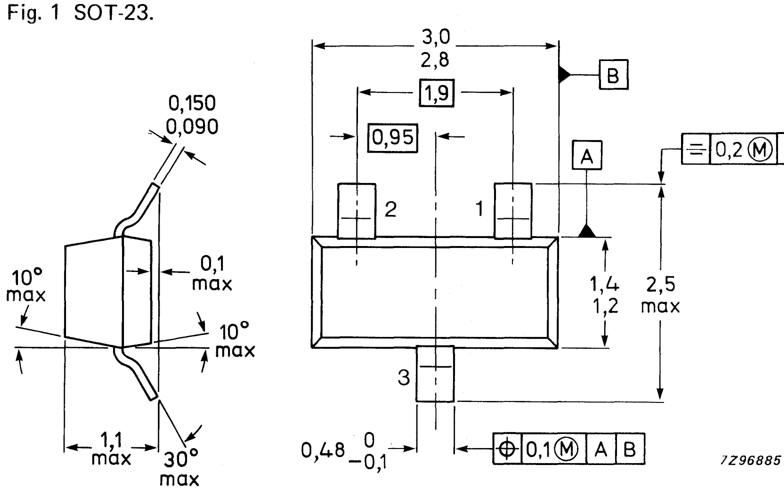
QUICK REFERENCE DATA

			BFR30	BFR31	
Drain-source voltage	$\pm V_{DS}$	max.	25		V
Gate-source voltage (open drain)	$-V_{GSO}$	max.	25		V
Total power dissipation up to T_{amb} = 65 °C	P_{tot}	max.	250		mW
Drain current V_{DS} = 10 V; V_{GS} = 0	I_{DSS}	>	4	1	mA
		<	10	5	mA
Transfer admittance (common source) I_D = 1 mA; V_{DS} = 10 V; f = 1 kHz	$\lvert y_{fs} \rvert$	>	1,0	1,5	mS
		<	4,0	4,5	mS

MECHANICAL DATA

Dimensions in mm

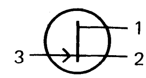
Fig. 1 SOT-23.



TOP VIEW

Marking code

BFR30 = M1
BFR31 = M2



See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage see Fig. 2	$\pm V_{DS}$	max.	25	V
Drain-gate voltage (open source) see Fig. 2	V_{DGO}	max.	25	V
Gate-source voltage (open drain) see Fig. 2	$-V_{GSO}$	max.	25	V
Drain current	I_D	max.	10	mA
Gate current	I_G	max.	5	mA
Total power dissipation up to T_{amb} = 65 °C**	P_{tot}	max.	250	mW
Storage temperature range	T_{stg}		−65 to + 175	°C
Junction temperature	T_j	max.	175	°C

THERMAL CHARACTERISTICS*

$T_j = P \times (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	60	K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280	K/W
From soldering points to ambient**	$R_{th\ s\text{-}a}$	=	90	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BFR30	BFR31	
Gate cut-off current $-V_{GS}$ = 10 V; V_{DS} = 0	$-I_{GSS}$	<	0,2	0,2	nA
Drain current V_{DS} = 10 V; V_{GS} = 0	I_{DSS}	> <	4 10	1 5	mA mA
Gate-source voltage I_D = 1 mA; V_{DS} = 10 V	$-V_{GS}$	> <	0,7 3,0	0 1,3	V V
I_D = 50 μA; V_{DS} = 10 V	$-V_{GS}$	<	4,0	2,0	V
Gate-source cut-off voltage I_D = 0,5 nA; V_{DS} = 10 V	$-V_{(P)GS}$	<	5	2,5	V
y parameters					
Transfer admittance at f = 1 kHz; T_{amb} = 25 °C I_D = 1 mA; V_{DS} = 10 V	$\lvert y_{fs}\rvert$	> <	1,0 4,0	1,5 4,5	mS mS
I_D = 200 μA; V_{DS} = 10 V	$\lvert y_{fs}\rvert$	>	0,5	0,75	mS
Output admittance at f = 1 kHz I_D = 1 mA; V_{DS} = 10 V	$\lvert y_{os}\rvert$	<	40	25	μS
I_D = 200 μA; V_{DS} = 10 V	$\lvert y_{os}\rvert$	<	20	15	μS

* See *Thermal characteristics.*
** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

y parameters (continued)

			BFR30	BFR31	
Input capacitance at f = 1 MHz					
I_D = 1 mA; V_{DS} = 10 V	C_{is}	<	4	4	pF
I_D = 200 μA; V_{DS} = 10 V	C_{is}	<	4	4	pF
Feedback capacitance at f = 1 MHz; T_{amb} = 25 °C					
I_D = 1 mA; V_{DS} = 10 V	C_{rs}	<	1,5	1,5	pF
I_D = 200 μA; V_{DS} = 10 V	C_{rs}	<	1,5	1,5	pF
Equivalent noise voltage					
I_D = 200 μA; V_{DS} = 10 V B = 0,6 to 100 Hz	V_n	<	0,5	0,5	μV

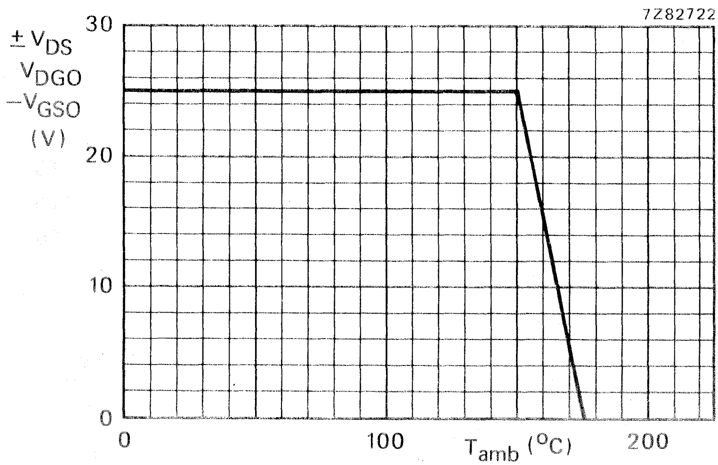


Fig. 2 Voltage derating curve.

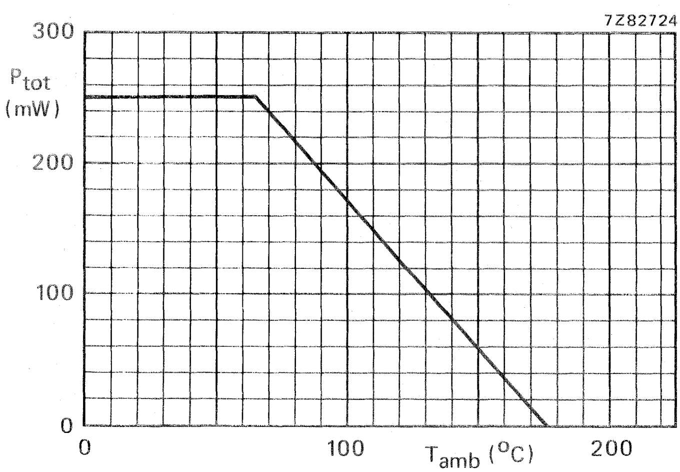


Fig. 3 Power derating curve.

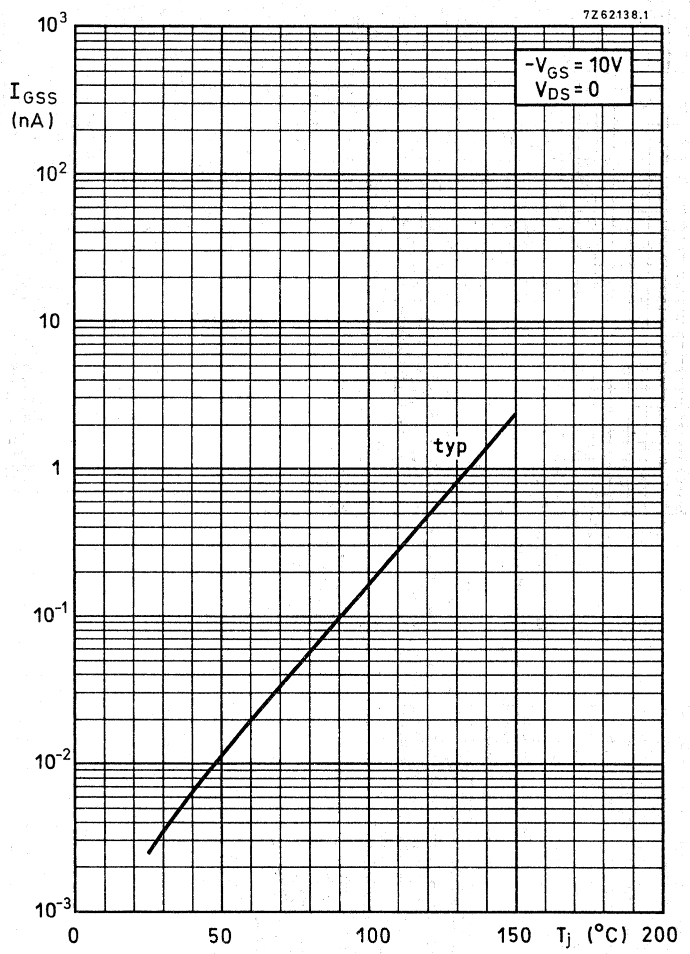

7Z62138.1
$-V_{GS} = 10V$
$V_{DS} = 0$
I_{GSS} (nA)
10^3
10^2
10
1
10^{-1}
10^{-2}
10^{-3}
typ
0
50
100
150
200
T_j (°C)

Fig. 4.

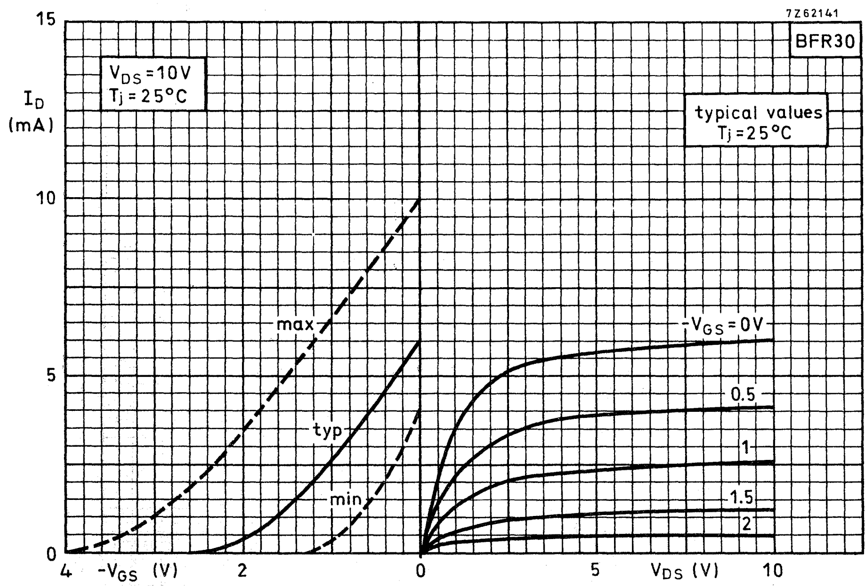

7Z62141
BFR30
V_{DS} = 10 V
T_j = 25 °C
I_D (mA)
typical values
T_j = 25 °C
max
typ
min
$-V_{GS}$ = 0 V
0.5
1
1.5
2
15
10
5
0
4
$-V_{GS}$ (V)
2
0
5
V_{DS} (V)
10

Fig. 5.

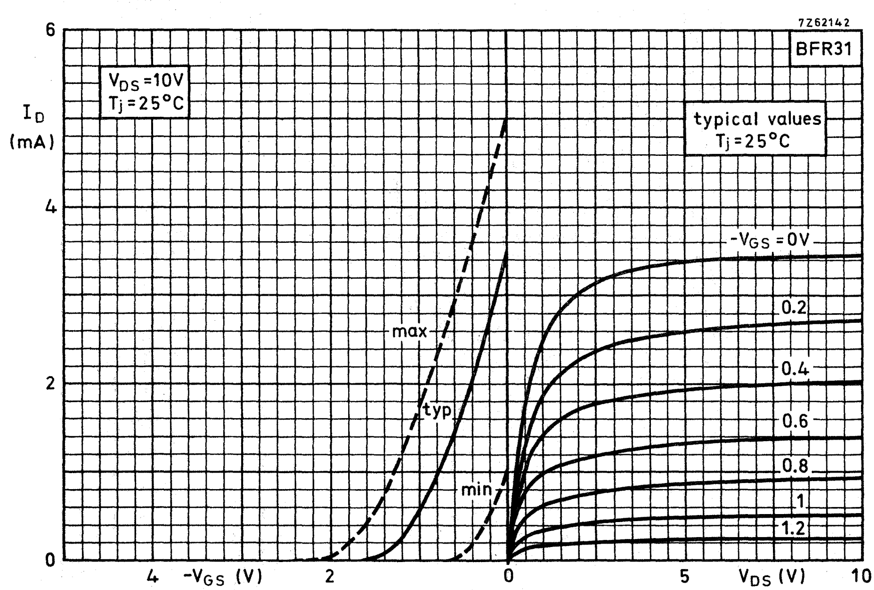

7Z62142
BFR31
V_{DS} = 10 V
T_j = 25 °C
I_D (mA)
typical values
T_j = 25 °C
max
typ
min
$-V_{GS}$ = 0 V
0.2
0.4
0.6
0.8
1
1.2
6
4
2
0
4
$-V_{GS}$ (V)
2
0
5
V_{DS} (V)
10

Fig. 6.

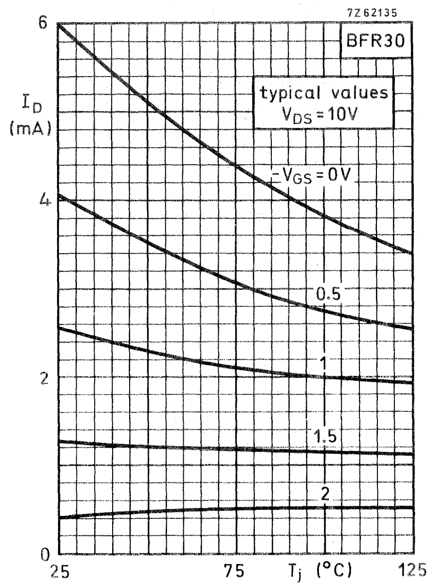


Fig. 7.

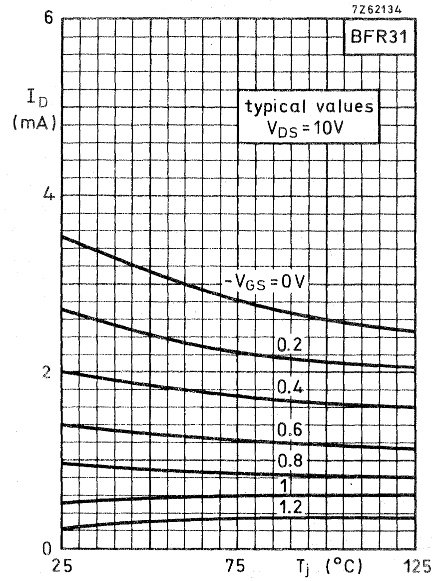


Fig. 8.

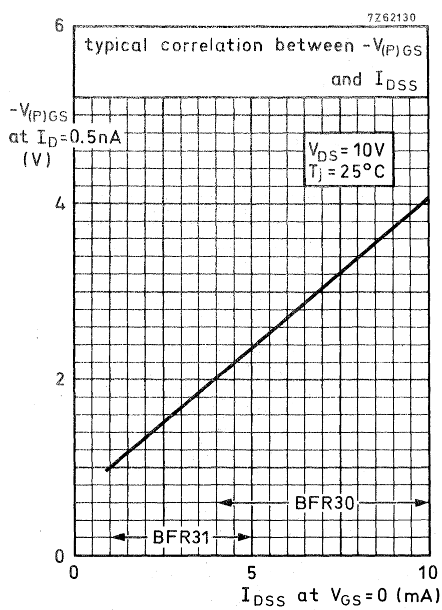


Fig. 9.

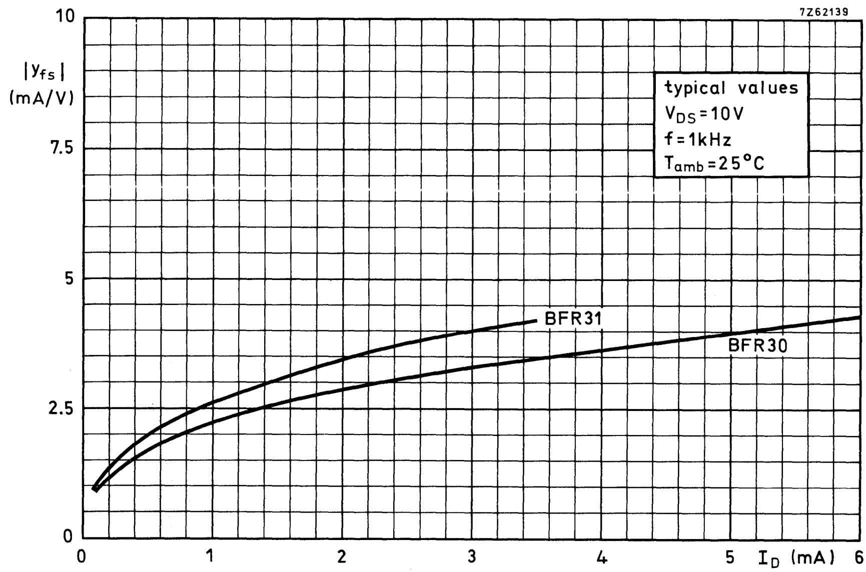

7Z62139
|yfs|
(mA/V)
10
7.5
5
2.5
0
typical values
VDS = 10V
f = 1kHz
Tamb = 25°C
BFR31
BFR30
0
1
2
3
4
5
ID (mA)
6

Fig. 10.

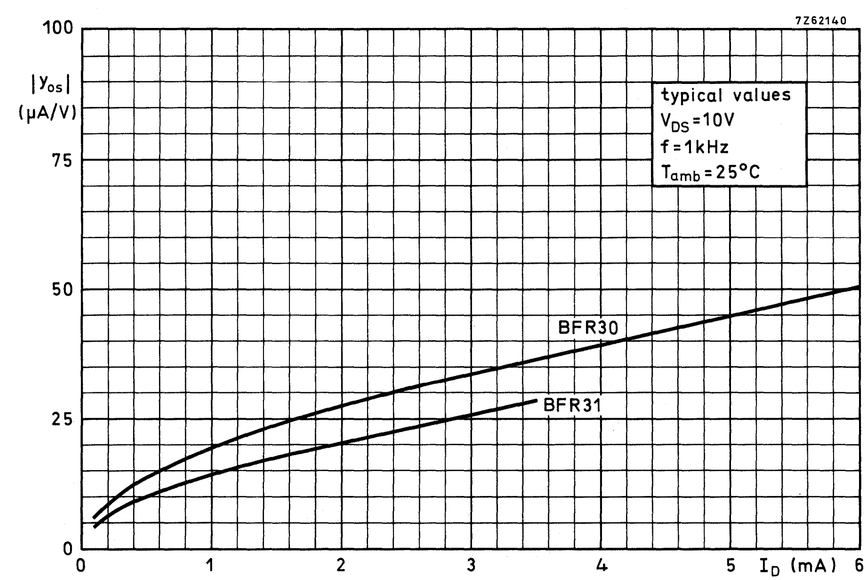

7Z62140
|yos|
(μA/V)
100
75
50
25
0
typical values
VDS = 10V
f = 1kHz
Tamb = 25°C
BFR30
BFR31
0
1
2
3
4
5
ID (mA)
6

Fig. 11.

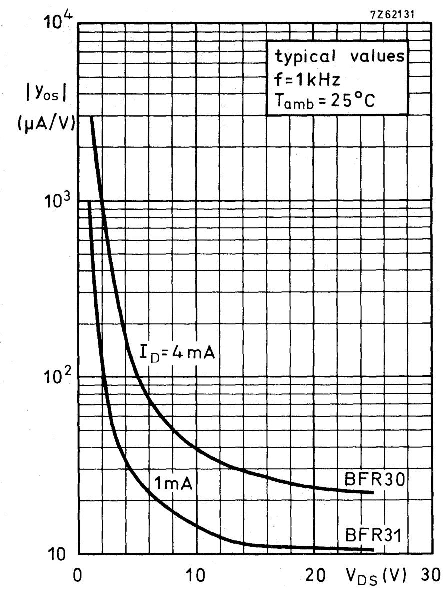


Fig. 12.

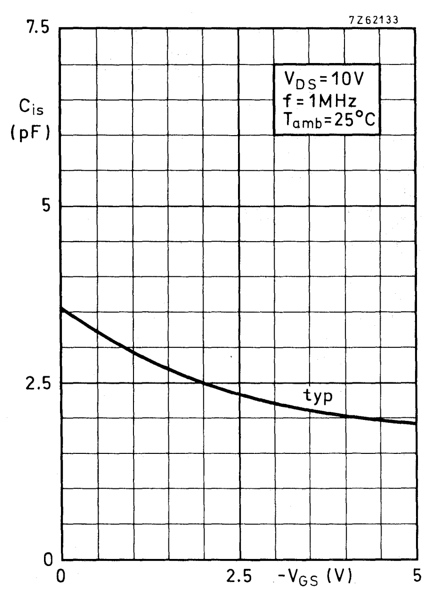


Fig. 13.

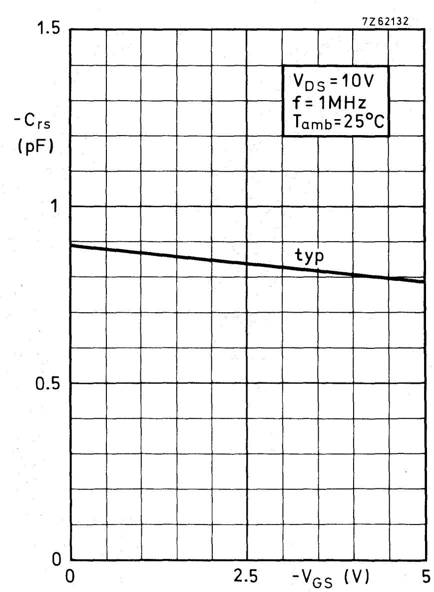


Fig. 14.

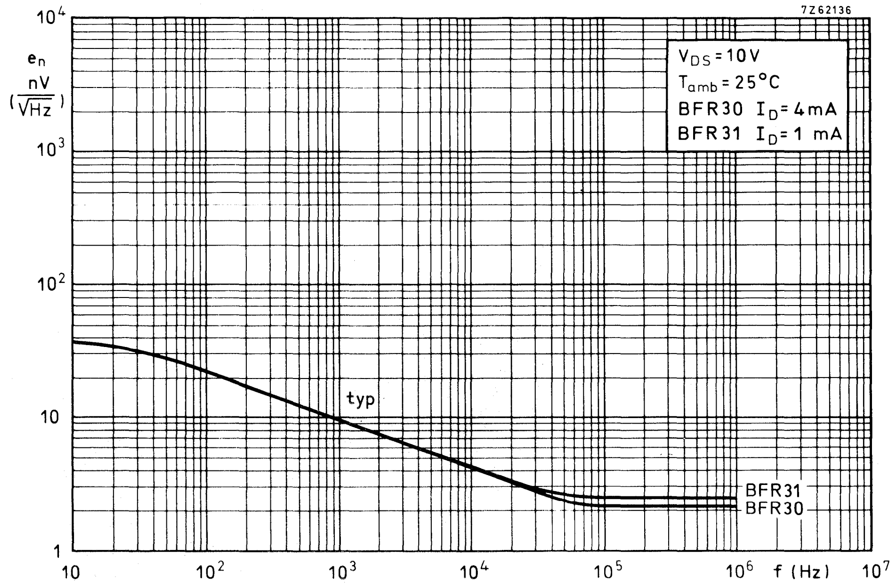

7Z62136
e_n
$\left(\frac{nV}{\sqrt{Hz}}\right)$
$V_{DS} = 10V$
$T_{amb} = 25°C$
BFR30 $I_D = 4mA$
BFR31 $I_D = 1 mA$
typ
BFR31
BFR30
f (Hz)
10^4
10^3
10^2
10
1
10
10^2
10^3
10^4
10^5
10^6
10^7

Fig. 15.

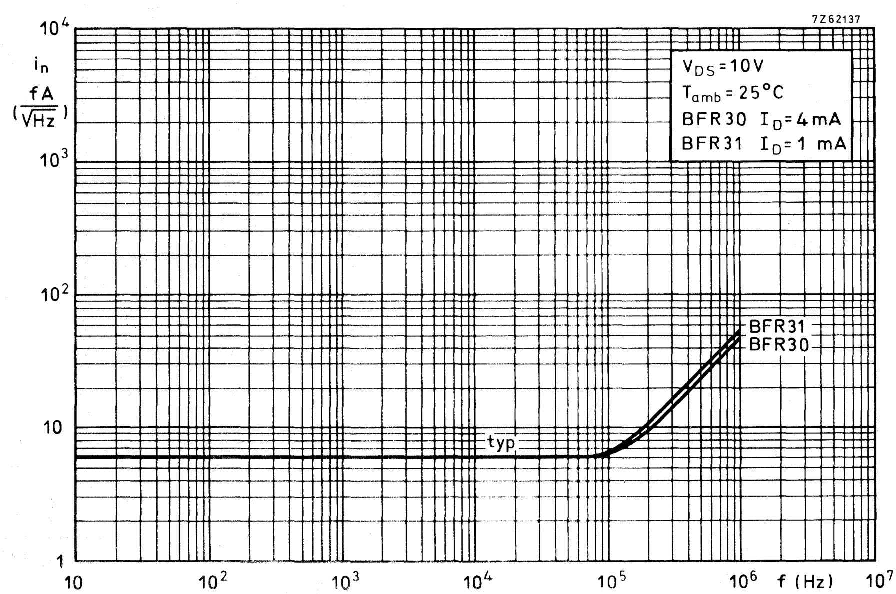

7Z62137
i_n
$\left(\frac{fA}{\sqrt{Hz}}\right)$
$V_{DS} = 10V$
$T_{amb} = 25°C$
BFR30 $I_D = 4mA$
BFR31 $I_D = 1 mA$
typ
BFR31
BFR30
f (Hz)
10^4
10^3
10^2
10
1
10
10^2
10^3
10^4
10^5
10^6
10^7

Fig. 16.

N-P-N H.F. WIDEBAND TRANSISTOR

N-P-N multi-emitter transistor in a plastic SOT-23 envelope intended for application in thick and thin-film circuits. The transistor has very low intermodulation distortion and very high power gain. It is primarily intended for:
- Wideband vertical amplifiers in high speed oscilloscopes.
- Television distribution amplifiers.

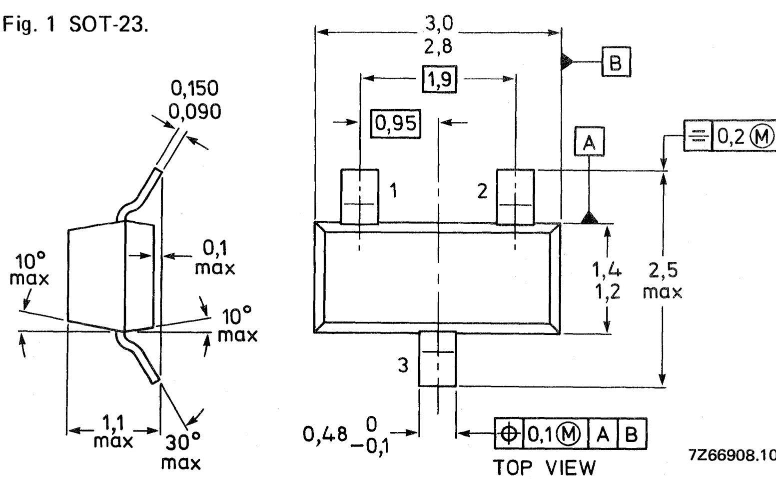
QUICK REFERENCE DATA

Collector-base voltage (open emitter)	V_{CBO}	max.	18	V
Collector-emitter voltage (open base)	V_{CEO}	max.	10	V
Collector current (peak value; f > 1 MHz)	I_{CM}	max.	100	mA
Total power dissipation up to T_{amb} = 65 °C	P_{tot}	max.	250	mW
Junction temperature	T_j	max.	175	°C
Feedback capacitance at f = 1 MHz I_C = 2 mA; V_{CE} = 5 V	C_{re}	typ.	0,9	pF
Transition frequency at f = 500 MHz I_C = 25 mA; V_{CE} = 5 V	f_T	typ.	2,0	GHz
Max. unilateral power gain I_C = 30 mA; V_{CE} = 5 V; f = 200 MHz	G_{UM}	typ.	22	dB
I_C = 30 mA; V_{CE} = 5 V; f = 800 MHz	G_{UM}	typ.	10,5	dB
Intermodulation distortion at T_{amb} = 25 °C I_C = 30 mA; V_{CE} = 5 V; R_L = 37,5 Ω V_o = 100 mV at f_p = 183 MHz V_o = 100 mV at f_q = 200 MHz measured at $f_{(2q-p)}$ = 217 MHz	d_{im}	typ.	−60	dB

MECHANICAL DATA

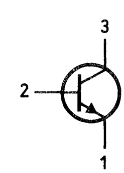
Dimensions in mm

Fig. 1 SOT-23.



Marking code

BFR53 = N1



If required, the R-version (reverse pinning) is available on request.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter) see Fig. 3	V_{CBO}	max.	18	V
Collector-emitter voltage (open base) see Fig. 3	V_{CEO}	max.	10	V
Emitter-base voltage (open collector) see Fig. 3	V_{EBO}	max.	2,5	V
Collector current (d.c.)	I_C	max.	50	mA
Collector current (peak value: $f > 1$ MHz)	I_{CM}	max.	100	mA
Total power dissipation up to T_{amb} = 65 °C**	P_{tot}	max.	250	mW
Storage temperature	T_{stg}	−65 to	+175	°C
Junction temperature	T_j	max.	175	°C

THERMAL RESISTANCE *

From junction to ambient**	$R_{th\ j\text{-}a}$	=	430	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current				
$I_E = 0$; $V_{CB} = 10$ V	I_{CBO}	max.	50	nA
D.C. current gain				
$I_C = 25$ mA; $V_{CE} = 5$ V	h_{FE}	min.	25	
$I_C = 50$ mA; $V_{CE} = 5$ V	h_{FE}	min.	25	
Transition frequency at f = 500 MHz				
$I_C = 25$ mA; $V_{CE} = 5$ V	f_T	typ.	2,0	GHz
Collector capacitance at f = 1 MHz				
$I_E = I_e = 0$; $V_{CB} = 5$ V	C_c	typ.	0,9	pF
Emitter capacitance at f = 1 MHz				
$I_C = I_c = 0$; $V_{EB} = 0{,}5$ V	C_e	typ.	1,5	pF
Feedback capacitance at f = 1 MHz				
$I_C = 2$ mA; $V_{CE} = 5$ V; $T_{amb} = 25$ °C	C_{re}	typ.	0,9	pF

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

Noise figure at f = 500 MHz ▲

I_C = 2 mA; V_{CE} = 5 V; T_{amb} = 25 °C G_S = 20 mS; B_S is tuned	F	max.	5,0 dB

Max. unilateral power gain (s_{re} assumed to be zero)

$$G_{UM} = 10 \log \frac{|s_{fe}|^2}{[1-|s_{ie}|^2]\,[1-|s_{oe}|^2]}$$

I_C = 30 mA; V_{CE} = 5 V; f = 200 MHz; T_{amb} = 25 °C	G_{UM}	typ.	22 dB
I_C = 30 mA; V_{CE} = 5 V; f = 800 MHz; T_{amb} = 25 °C	G_{UM}	typ.	10,5 dB

Intermodulation distortion ▲

I_C = 30 mA; V_{CE} = 5 V; R_L = 37,5 Ω

V_o = 100 mV at f_p = 183 MHz
V_o = 100 mV at f_q = 200 MHz

measured at $f_{(2q-p)}$ = 217 MHz	d_{im}	typ.	−60 dB

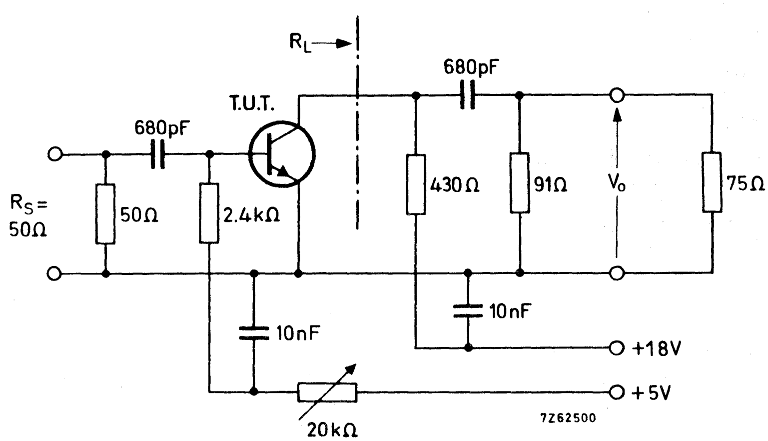


Fig. 2 Test circuit.

▲ Crystal mounted in a BFW30 envelope.

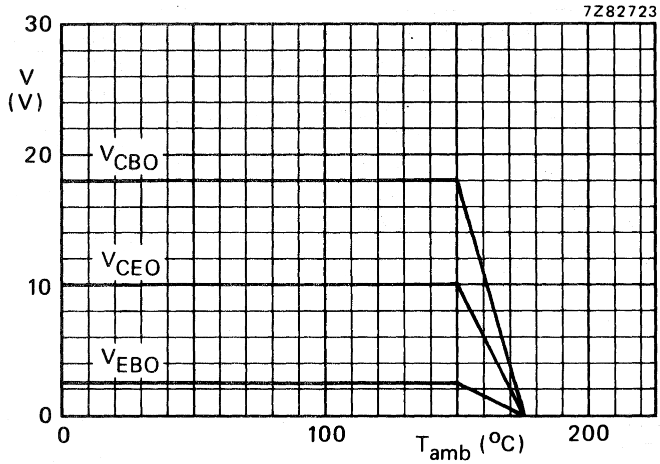


Fig. 3 Voltage derating curves.

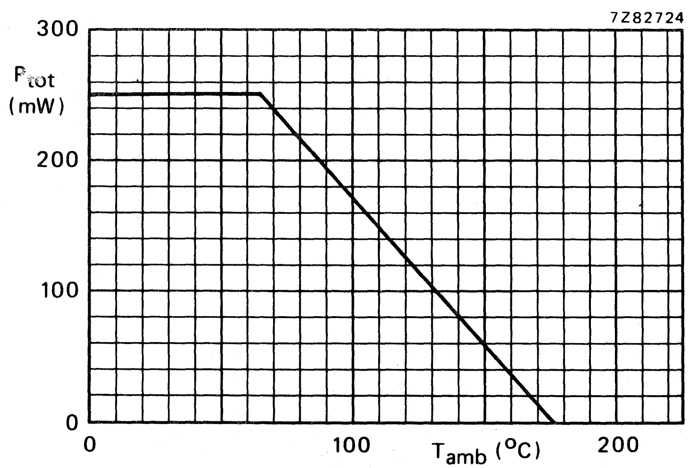


Fig. 4 Power derating curve.

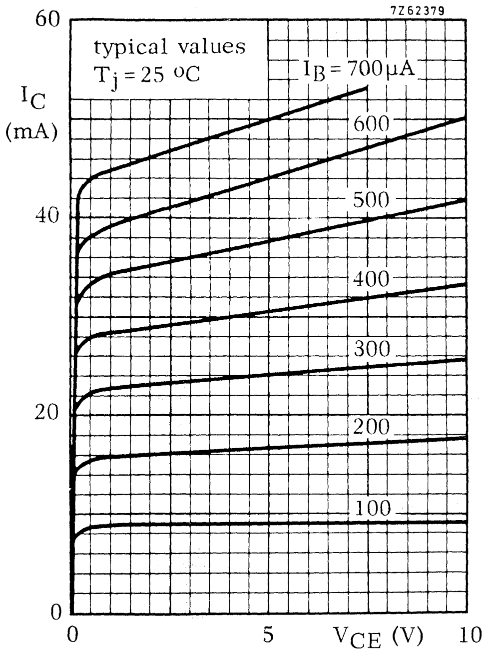


Fig. 5 $T_j = 25\ ^oC$; typical values.

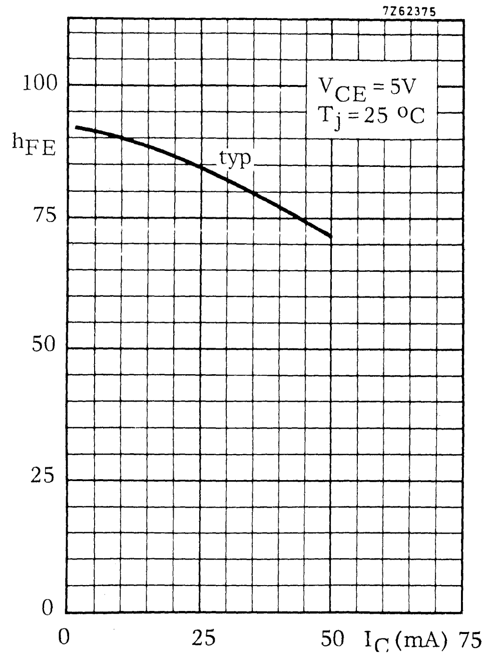


Fig. 6 $V_{CE} = 5$ V; $T_j = 25\ ^oC$; typical values.

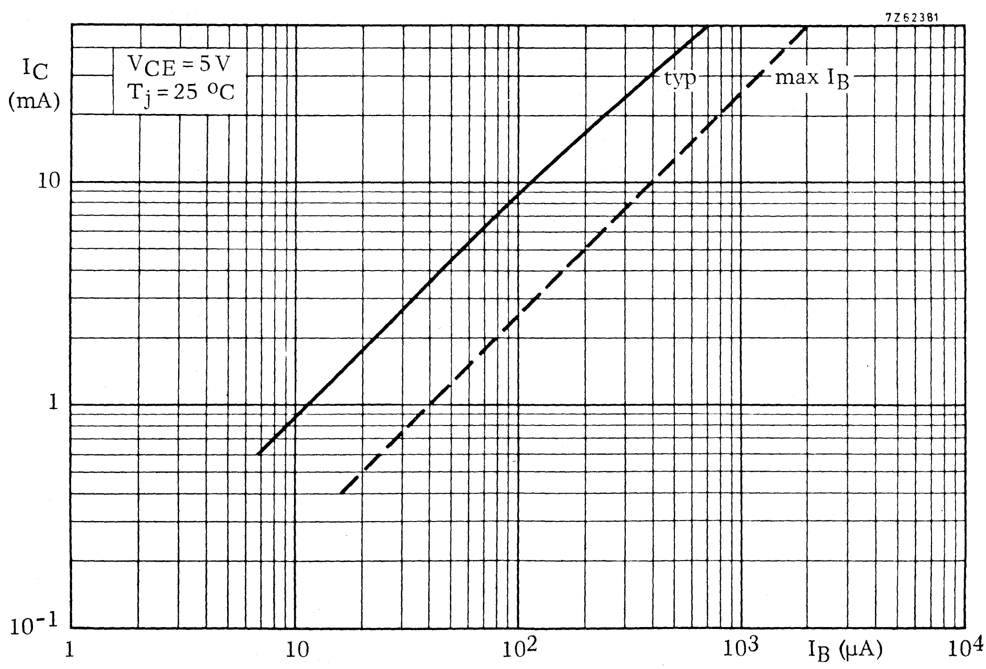


Fig. 7 $V_{CE} = 5$ V; $T_j = 25\ ^oC$.

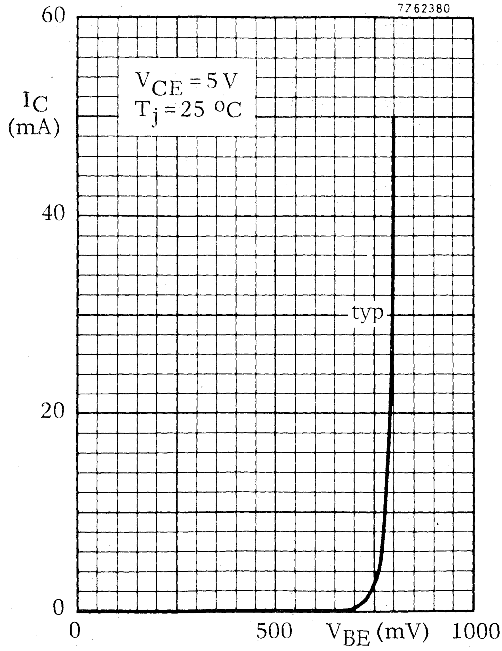


Fig. 8 V_{CE} = 5 V; T_j = 25 °C; typical values.

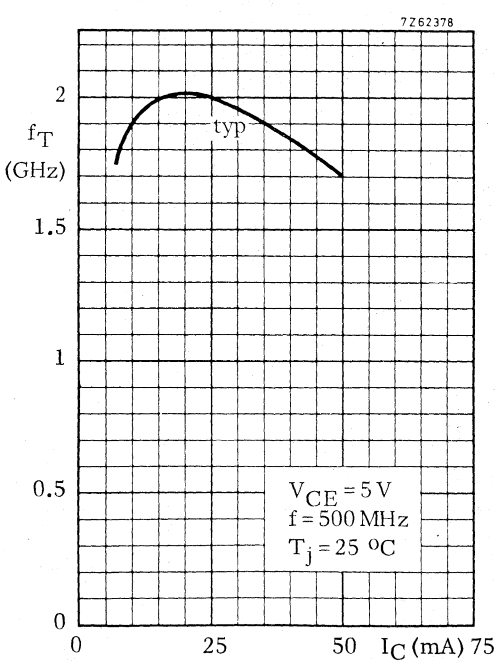


Fig. 9 V_{CE} = 5 V; f = 500 MHz; T_j = 25 °C; typical values.

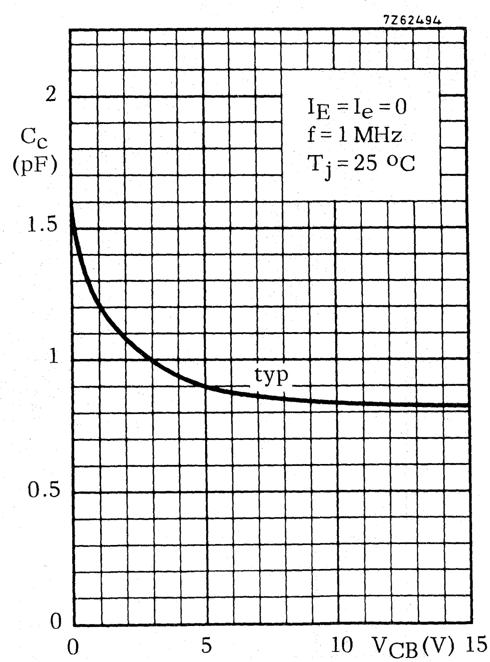


Fig. 10 $I_E = i_e = 0$; f = 1 MHz; T_j = 25 °C; typical values.

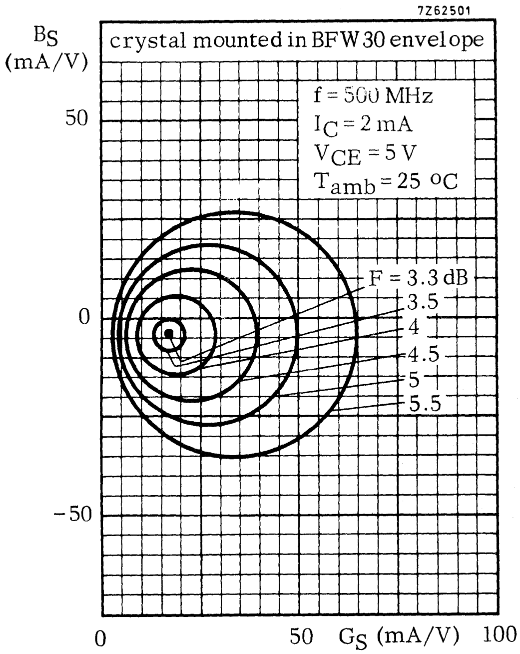


Fig. 11 Circles of constant noise figure; V_{CE} = 5 V; I_C = 2 mA; f = 500 MHz; T_{amb} = 25 °C; typ. values.

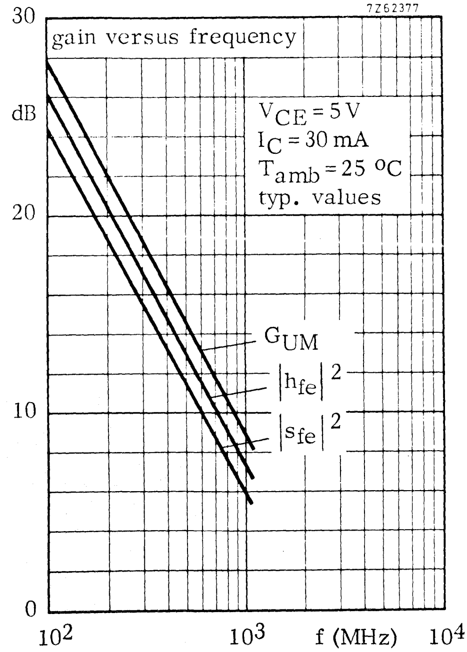


Fig. 12 V_{CE} = 5 V; I_C = 30 mA; T_{amb} = 25 °C; typical values.

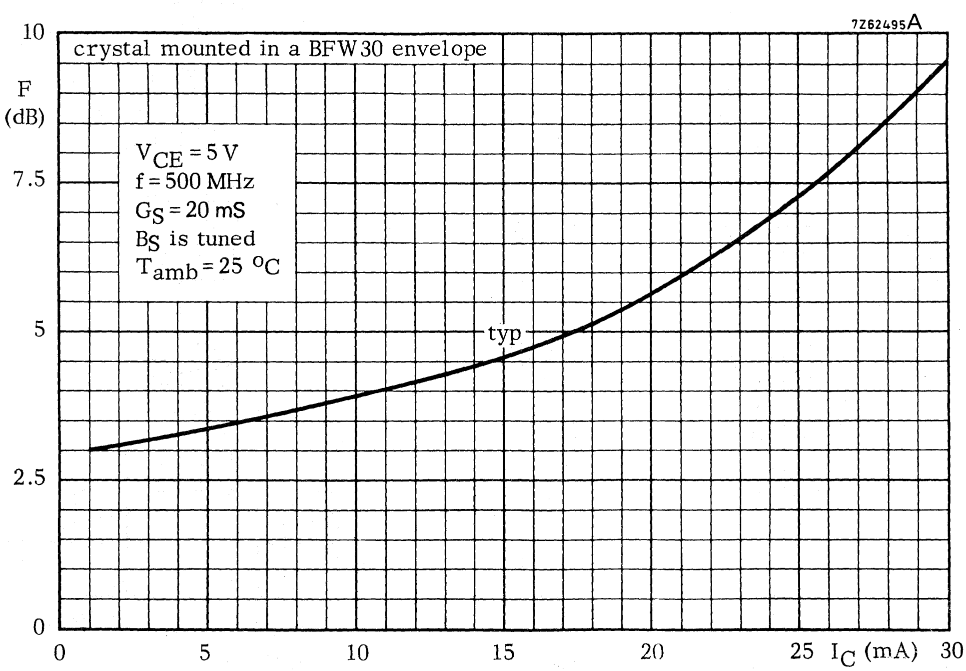


Fig. 13 V_{CE} = 5 V; f = 500 MHz; G_S = 20 mS; B_S = tuned; T_{amb} = 25 °C; typical values.

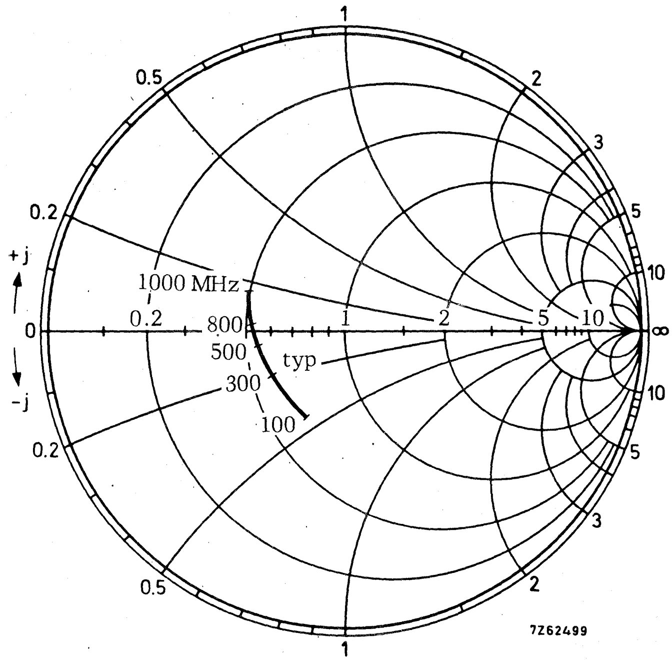


Fig. 14 V_{CE} = 5 V; I_C = 30 mA; T_{amb} = 25 °C; typical values.

Input impedance derived from input reflection coefficient s_{ie} coordinates in ohm x 50.

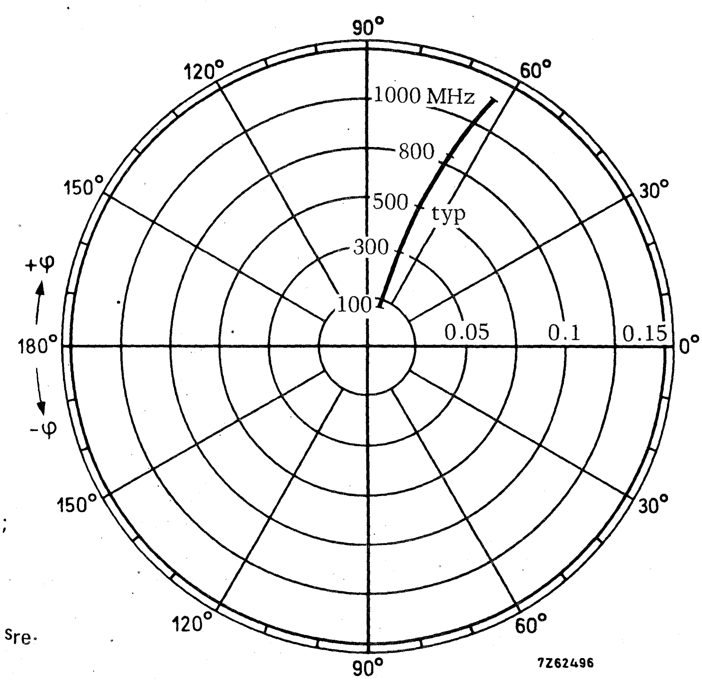


Fig. 15 V_{CE} = 5 V; I_C = 30 mA; T_{amb} = 25 °C; typical values.

Reverse transmission coefficient s_{re}.

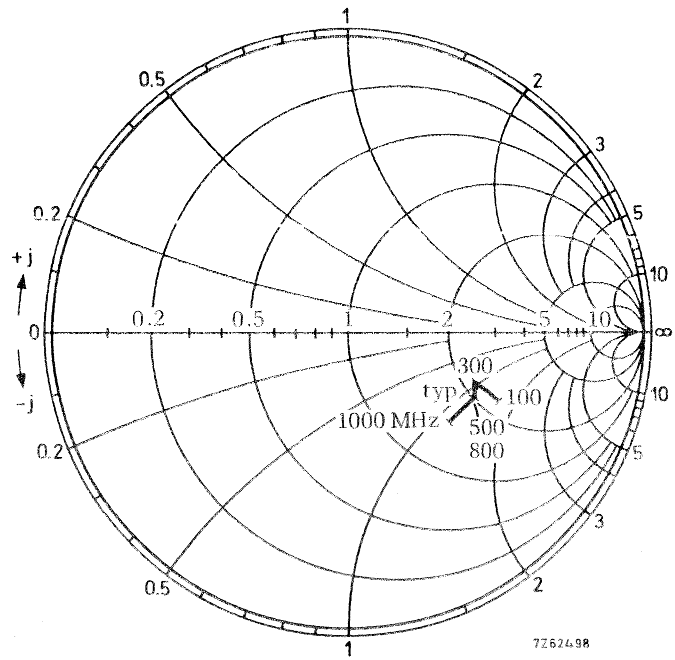


Fig. 16 V_{CE} = 5 V; I_C = 30 mA; T_{amb} = 25 °C; typical values.

Output impedance derived from output reflection coefficient s_{oe} coordinates in ohm x 50.

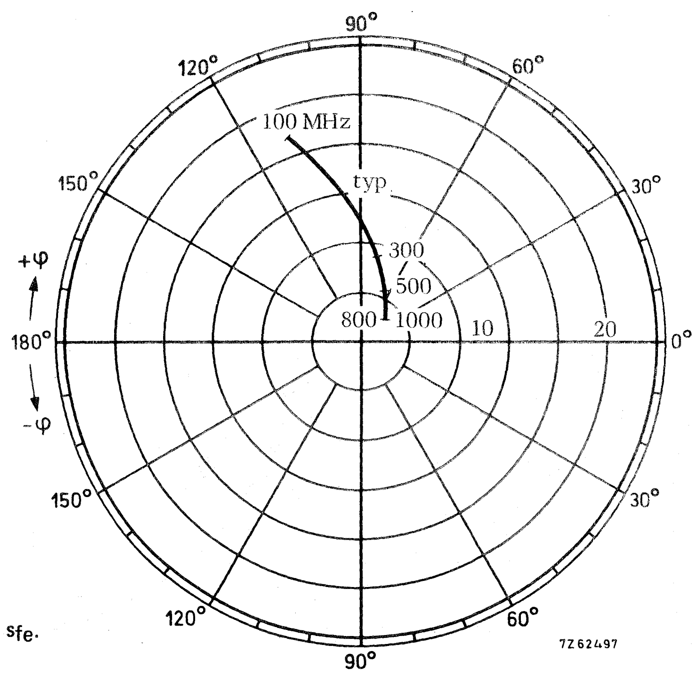


Fig. 17 V_{CE} = 5 V; I_C = 30 mA; T_{amb} = 25 °C; typical values.

Forward transmission coefficient s_{fe}.

N-P-N 1 GHz WIDEBAND TRANSISTOR

N-P-N transistor in a plastic SOT-23 envelope. It is primarily intended for use in u.h.f. and microwave amplifiers in thick and thin-film circuits, such as in aerial amplifiers, radar systems, oscilloscopes, spectrum analysers etc. The transistor features low intermodulation distortion and high power gain; thanks to its very high transition frequency, it also has excellent wideband properties and low noise up to high frequencies.

P-N-P complement is BFT92.

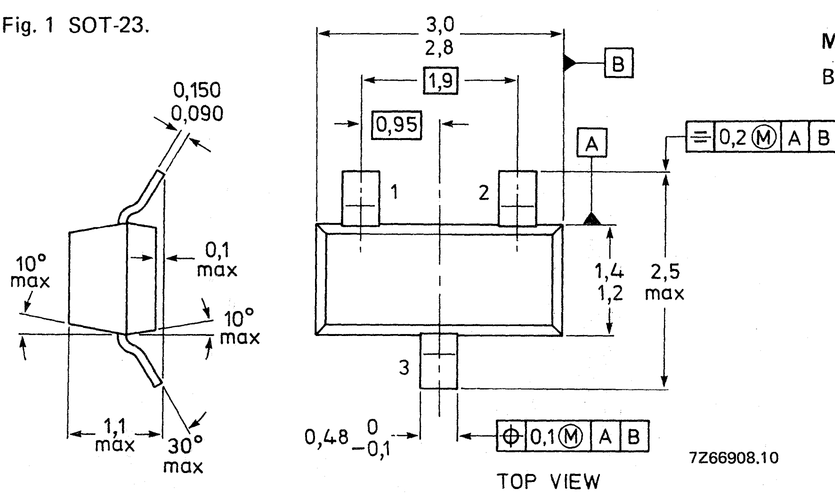
QUICK REFERENCE DATA

Collector-base voltage (open emitter)	V_{CBO}	max.	20	V
Collector-emitter voltage (open base)	V_{CEO}	max.	15	V
Collector current (d.c.)	I_C	max.	25	mA
Total power dissipation up to T_{amb} = 60 °C	P_{tot}	max.	200	mW
Junction temperature	T_j	max.	150	°C
Transition frequency at f = 500 MHz I_C = 14 mA; V_{CE} = 10 V	f_T	typ.	5,0	GHz
Feedback capacitance at f = 1 MHz I_C = 2 mA; V_{CE} = 10 V	C_{re}	typ.	0,4	pF
Noise figure at optimum source impedance I_C = 2 mA; V_{CE} = 10 V; f = 500 MHz	F	typ.	2,4	dB
Max. unilateral power gain I_C = 14 mA; V_{CE} = 10 V; f = 500 MHz	G_{UM}	typ.	18,0	dB
Output voltage at d_{im} = −60 dB (see Fig. 2) I_C = 14 mA; V_{CE} = 10 V; R_L = 75 Ω; T_{amb} = 25 °C $f_{(p+q-r)}$ = 493,25 MHz	V_o	typ.	150	mV

MECHANICAL DATA

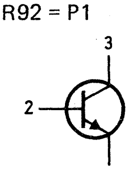
Dimensions in mm

Fig. 1 SOT-23.



Marking code

BFR92 = P1



If required, the R-version (reverse pinning) is available on request.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	V_{CBO}	max.	20	V
Collector-emitter voltage (open base)	V_{CEO}	max.	15	V
Emitter-base voltage (open collector)	V_{EBO}	max.	2	V
Collector current (d.c.)	I_C	max.	25	mA
Total power dissipation up to T_{amb} = 60 °C**	P_{tot}	max.	200	mW
Storage temperature	T_{stg}		−65 to +150	°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE*

From junction to ambient**	$R_{th\ j\text{-}a}$	=	430	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current I_E = 0; V_{CB} = 10 V	I_{CBO}	max.	50	nA
D.C. current gain I_C = 14 mA; V_{CE} = 10 V	h_{FE}	min. typ.	25 50	
Transition frequency at f = 500 MHz I_C = 14 mA; V_{CE} = 10 V	f_T	typ.	5,0	GHz
Collector capacitance at f = 1 MHz I_E = I_e = 0; V_{CB} = 10 V	C_c	typ.	0,75	pF
Emitter capacitance at f = 1 MHz I_C = I_c = 0; V_{EB} = 0,5 V	C_e	typ.	0,8	pF
Feedback capacitance at f = 1 MHz I_C = 2 mA; V_{CE} = 10 V; T_{amb} = 25 °C	C_{re}	typ.	0,4	pF

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

Noise figure at optimum source impedance*			
I_C = 2 mA; V_{CE} = 10 V; f = 500 MHz; T_{amb} = 25 °C	F	typ.	2,4 dB
Max. unilateral power gain (s_{re} assumed to be zero)			
$G_{UM} = 10 \log \frac{\lvert s_{fe}\rvert^2}{[1-\lvert s_{ie}\rvert^2]\,[1-\lvert s_{oe}\rvert^2]}$			
I_C = 14 mA; V_{CE} = 10 V; f = 500 MHz; T_{amb} = 25 °C	G_{UM}	typ.	18,0 dB
Output voltage at d_{im} = −60 dB (see Fig. 2) (DIN 45004B; par. 6.3.: 3-tone)			
I_C = 14 mA; V_{CE} = 10 V; R_L = 75 Ω			
$V_p = V_o$ at d_{im} = −60 dB ; f_p = 495,25 MHz			
$V_q = V_o$ −6 dB ; f_q = 503,25 MHz			
$V_r = V_o$ −6 dB ; f_r = 505,25 MHz			
measured at $f_{(p+q-r)}$ = 493,25 MHz	V_o	typ.	150 mV

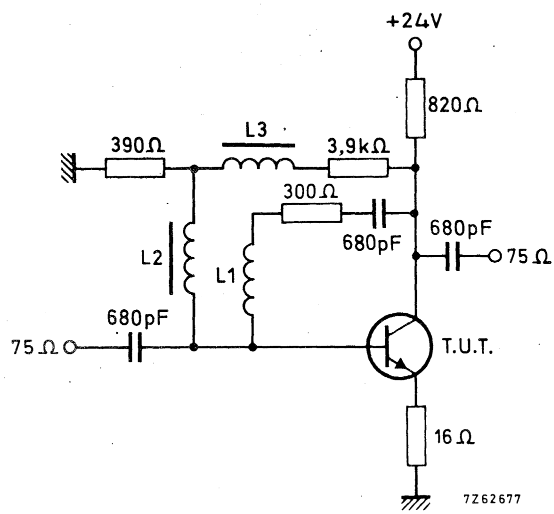


Fig. 2 Intermodulation test circuit.

L1 = 4 turns Cu wire (0,35 mm); winding pitch 1 mm; int. dia. 4 mm
L2 = L3 = 5 μH (code number: 3122 108 20150)

* Crystal mounted in a BFR90 envelope.

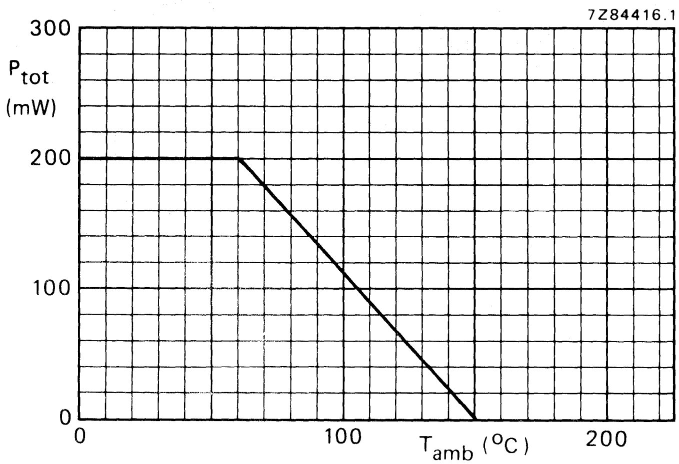


Fig. 3 Power derating curve.

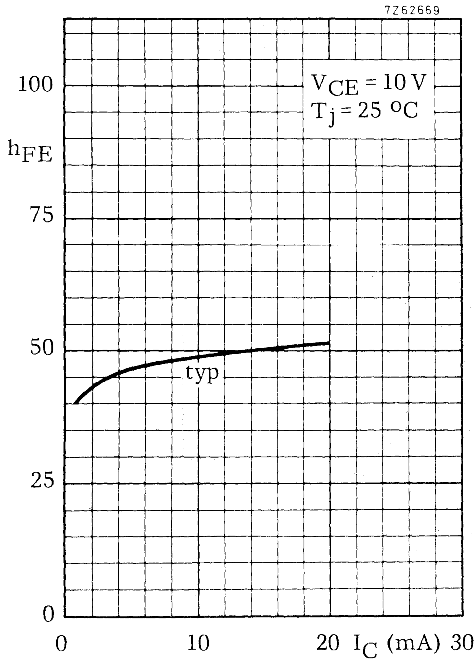


Fig. 4 V_{CE} = 10 V; T_j = 25 °C; typical values.

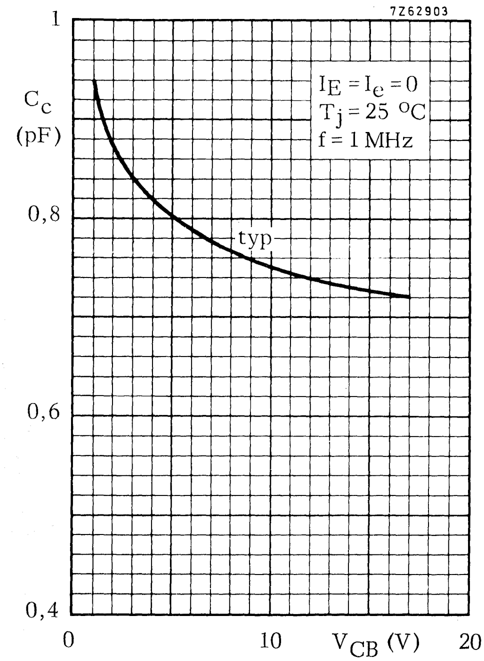


Fig. 5 $I_E = I_e = 0$; f = 1 MHz; T_j = 25 °C; typical values.

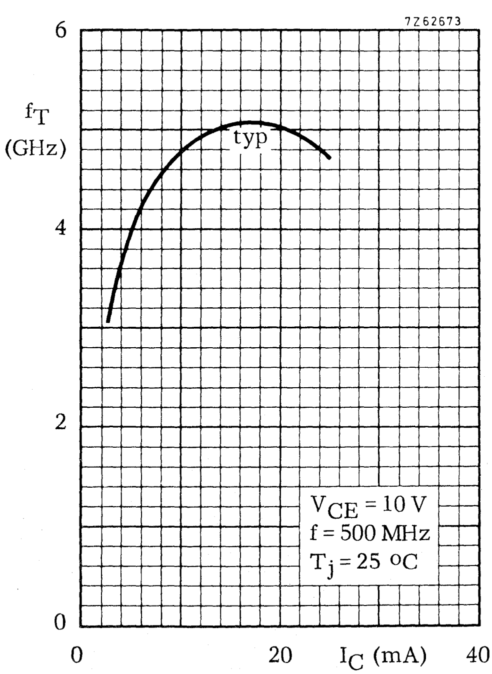


Fig. 6 V_{CE} = 10 V; f = 500 MHz; T_j = 25 °C; typical values.

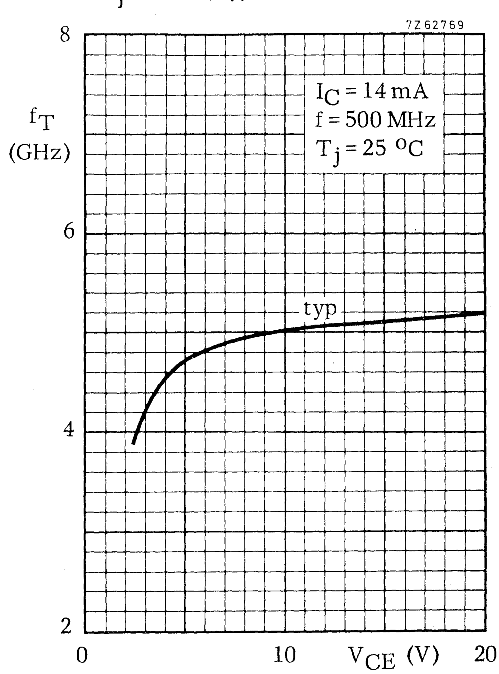


Fig. 7 I_C = 14 mA; f = 500 MHz; T_j = 25 °C; typical values.

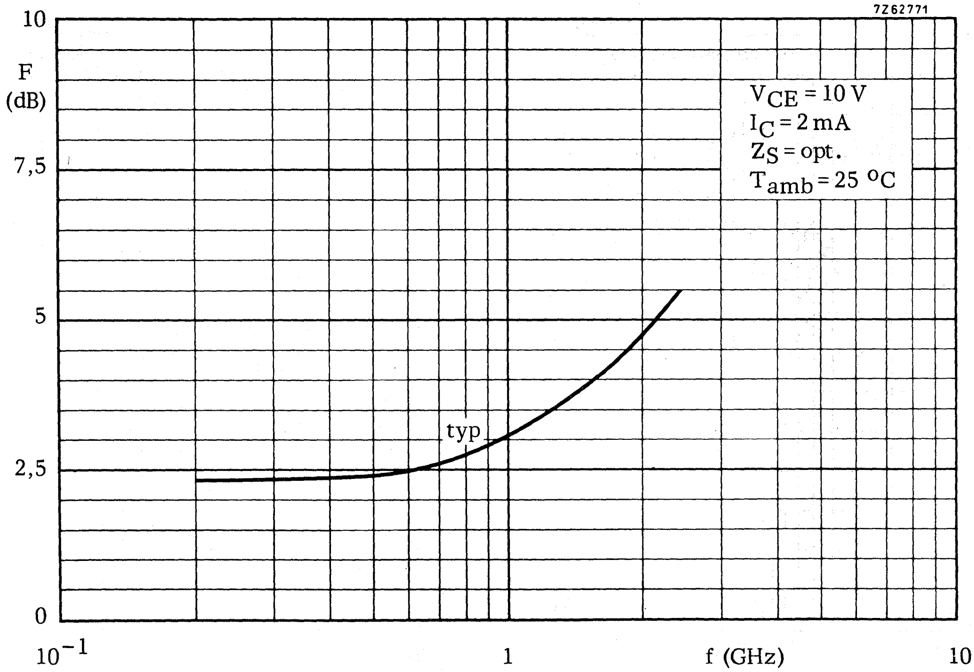


Fig. 8 $V_{CE} = 10$ V; $I_C = 2$ mA; Z_S = opt.; $T_{amb} = 25$ °C; typical values.

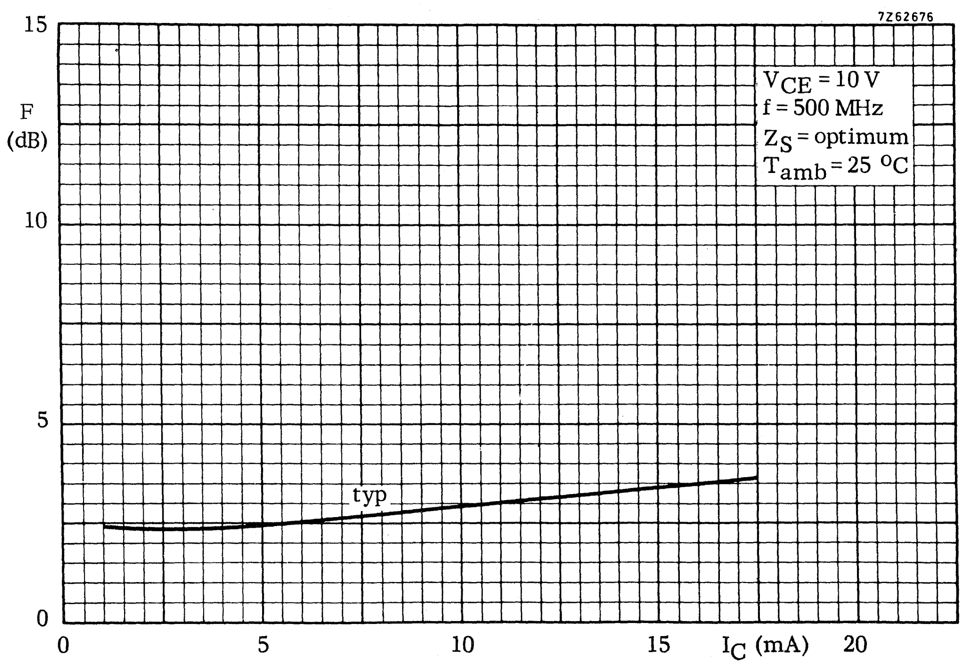


Fig. 9 $V_{CE} = 10$ V; f = 500 MHz; Z_S = opt.; $T_{amb} = 25$ °C; typical values.

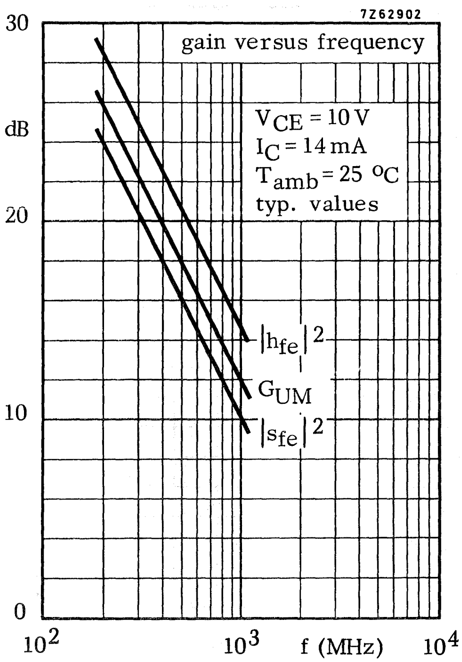


Fig. 10 V_{CE} = 10 V; I_C = 14 mA; T_{amb} = 25 °C; typical values.

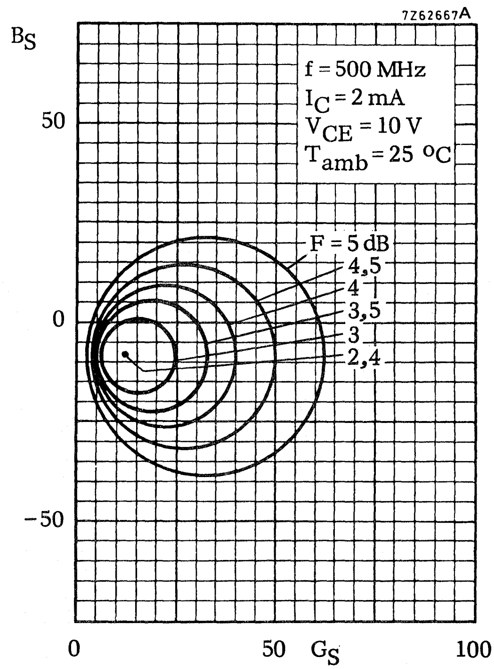


Fig. 11 Circles of constant noise figure; V_{CE} = 10 V; I_C = 2 mA; f = 500 MHz; T_{amb} = 25 °C; typical values.

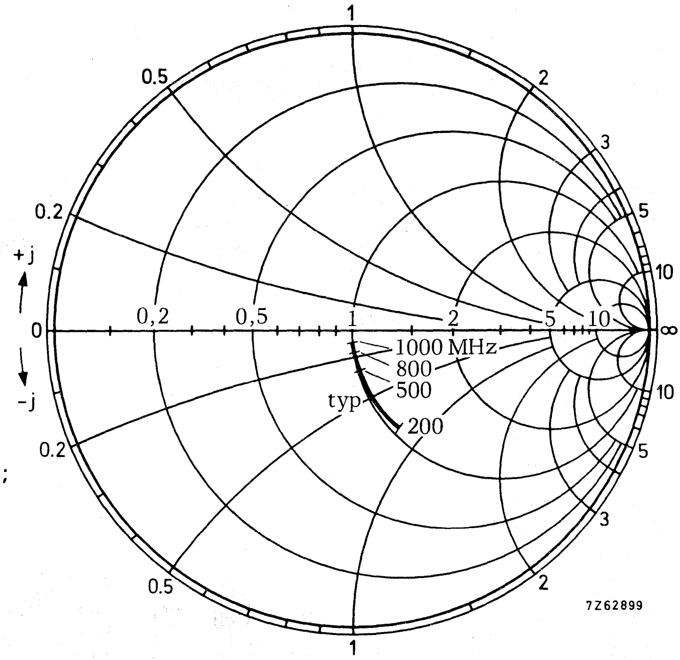


Fig. 12 V_{CE} = 10 V; I_C = 14 mA; T_{amb} = 25 °C; typical values.

Input impedance derived from input reflection coefficient s_{ie} coordinates in ohm x 50

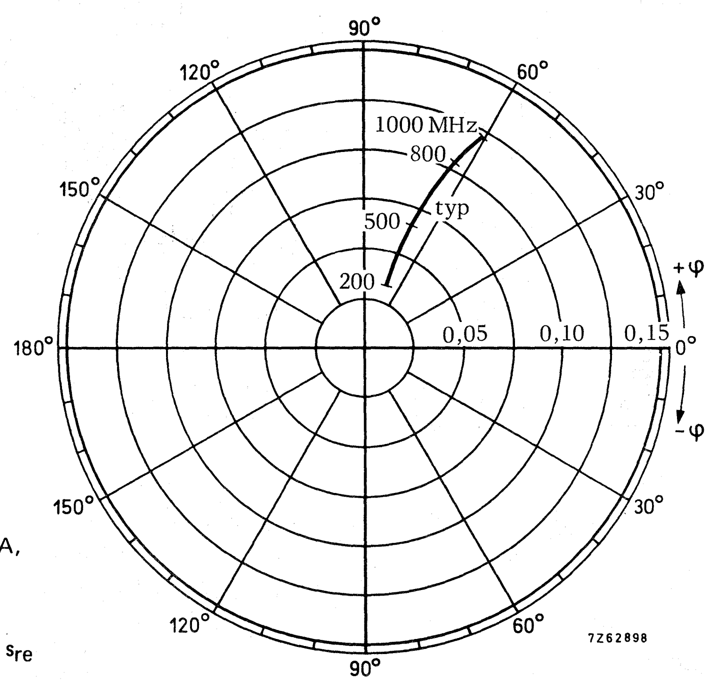


Fig. 13 V_{CE} = 10 V; I_C = 14 mA, T_{amb} = 25 °C; typical values.

Reverse transmission coefficient s_{re}

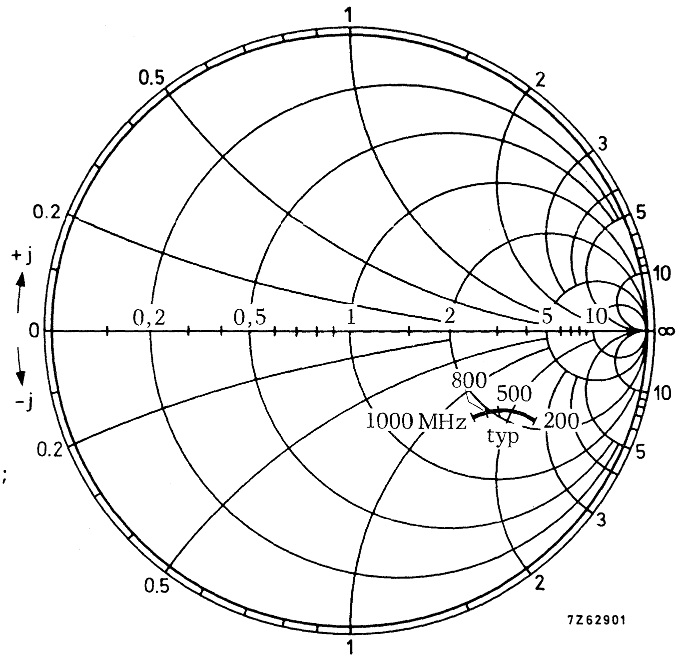


Fig. 14 V_{CE} = 10 V; I_C = 14 mA; T_{amb} = 25 °C; typical values.

Output impedance derived from output reflection coefficient s_{oe} coordinates in ohm x 50

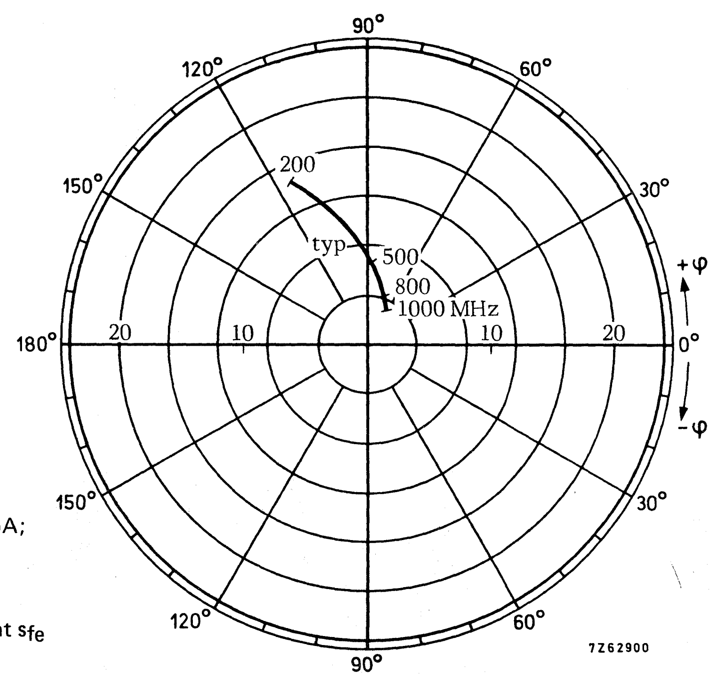


Fig. 15 V_{CE} = 10 V; I_C = 14 mA; T_{amb} = 25 °C; typical values.

Forward transmission coefficient s_{fe}

N-P-N 1 GHz WIDEBAND TRANSISTOR

N-P-N transistor in a plastic SOT-23 envelope. It is primarily intended for use in v.h.f./u.h.f. broadband amplifiers. The transistor features:

- low noise;
- low intermodulation distortion;
- high power gain.

P-N-P complement is BFT92

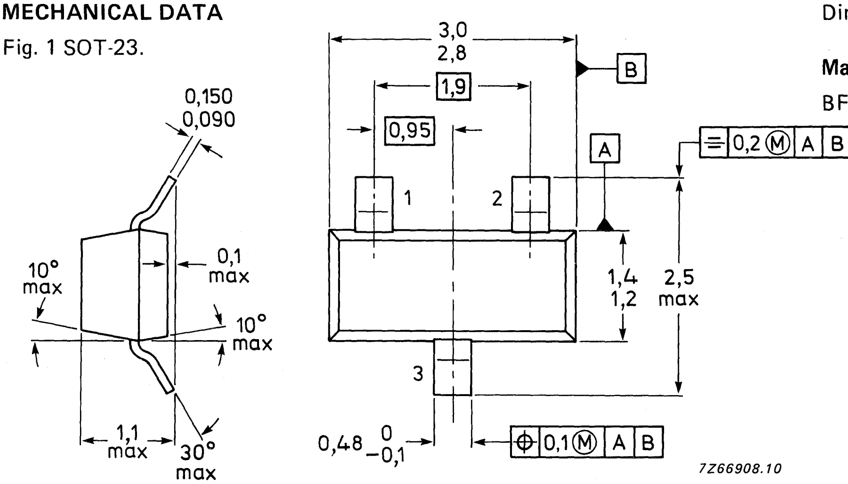
QUICK REFERENCE DATA

Collector-base voltage (open emitter)	V_{CBO}	max.	20	V
Collector-emitter voltage (open-base)	V_{CEO}	max.	15	V
Collector current (d.c.)	I_C	max.	25	mA
Total power dissipation up to T_{amb} = 60 °C	P_{tot}	max.	200	mW
Junction temperature	T_j	max.	150	°C
Transition frequency at f = 500 MHz I_C = 14 mA; V_{CE} = 10 V	f_T	typ.	5,0	GHz
Feedback capacitance at f = 1 MHz I_C = 0; V_{CE} = 10 V	C_{re}	typ.	0,35	pF
Noise figure at R_S = 60 Ω I_C = 4 mA; V_{CE} = 10 V; f = 800 MHz	F	typ.	1,8	dB
Output voltage at d_{im} = −60 dB I_C = 14 mA; V_{CE} = 10 V; R_L = 75 Ω $f_{(p+q-r)}$ = 793,25 MHz	V_o	typ.	150	mV

MECHANICAL DATA

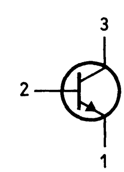
Dimensions in mm

Fig. 1 SOT-23.



Marking code

BFR92A = P2



TOP VIEW

If required, the R-version (reverse pinning) is available on request.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	V_{CBO}	max.	20	V
Collector-emitter voltage (open base)	V_{CEO}	max.	15	V
Emitter-base voltage (open collector)	V_{EBO}	max.	2,0	V
Collector current (d.c.)	I_C	max.	25	mA
Total power dissipation up to T_{amb} = 60 °C**	P_{tot}	max.	200	mW
Storage temperature	T_{stg}		−65 to +150	°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE*

From junction to ambient**	$R_{th\ j\text{-}a}$	=	430	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current $I_E = 0$; $V_{CB} = 10$ V	I_{CBO}	max.	60	nA
D.C. current gain $I_C = 14$ mA; $V_{CE} = 10$ V	h_{FE}	min. typ.	40 90	
Transition frequency at f = 500 MHz $I_C = 14$ mA; $V_{CE} = 10$ V	f_T	typ.	5,0	GHz
Collector capacitance at f = 1 MHz $I_E = I_e = 0$; $V_{CB} = 10$ V	C_c	typ.	0,6	pF
Emitter capacitance at f = 1 MHz $I_C = I_c = 0$; $V_{EB} = 0{,}5$ V	C_e	typ.	1,2	pF
Feedback capacitance at f = 1 MHz $I_C = 0$; $V_{CE} = 10$ V; $T_{amb} = 25$ °C	C_{re}	typ.	0,35	pF
Noise figure at $T_{amb} = 25$ °C $I_C = 4$ mA; $V_{CE} = 10$ V; $R_S = 60\ \Omega$; f = 800 MHz	F	typ.	1,8	dB

Maximum unilateral power gain (s_{re} assumed to be zero)

$$G_{UM} = 10 \log \frac{|s_{fe}|^2}{[1-|s_{ie}|^2]\,[1-|s_{oe}|^2]}$$

$I_C = 14$ mA; $V_{CE} = 10$ V; f = 800 MHz; $T_{amb} = 25$ °C	G_{UM}	typ.	15,5	dB

* See *Thermal characteristics*.

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

Output voltage at d_{im} = −60 dB (see Figs 2 and 17)*
(DIN 45004B, par. 6.3: 3-tone)
I_C = 14 mA; V_{CE} = 10 V; R_L = 75 Ω; VSWR < 2; T_{amb} = 25 °C
$V_p = V_o$ at d_{im} = −60 dB; f_p = 795,25 MHz
$V_q = V_o$ −6 dB ; f_q = 803,25 MHz
$V_r = V_o$ −6 dB ; f_r = 805,25 MHz
Measured at $f_{(p+q-r)}$ = 793,25 MHz — V_o typ. 150 mV

Second harmonic distortion (see Figs 2 and 18)*
I_C = 14 mA; V_{CE} = 10 V; R_L = 75 Ω; VSWR < 2; T_{amb} = 25 °C
V_p = 60 mV at f_p = 250 MHz
V_q = 60 mV at f_q = 560 MHz
measured at $f_{(p+q)}$ = 810 MHz — d_2 typ. −50 dB

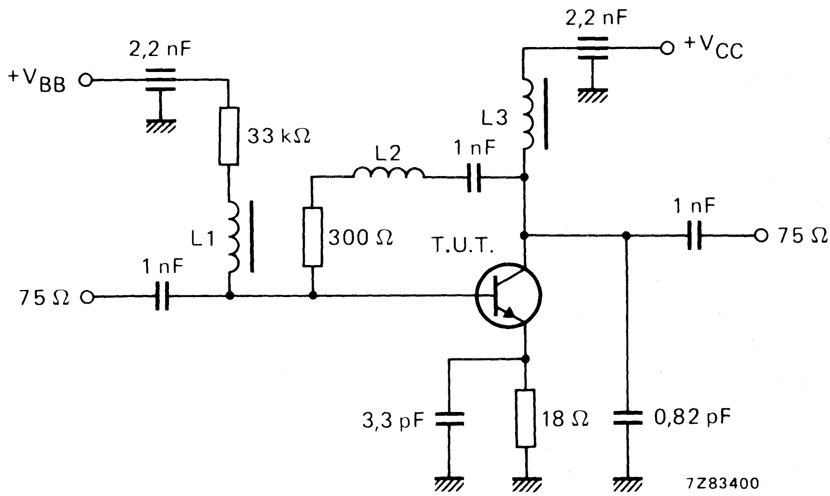


Fig. 2 Intermodulation distortion and second harmonic distortion MATV test circuit.

L1 = L3 = 5 μH micro choke
L2 = 3 turns Cu wire (0,4 mm); internal diameter 3 mm; winding pitch 1 mm

* Measured on same crystal in a SOT-37 envelope (BFR90A).

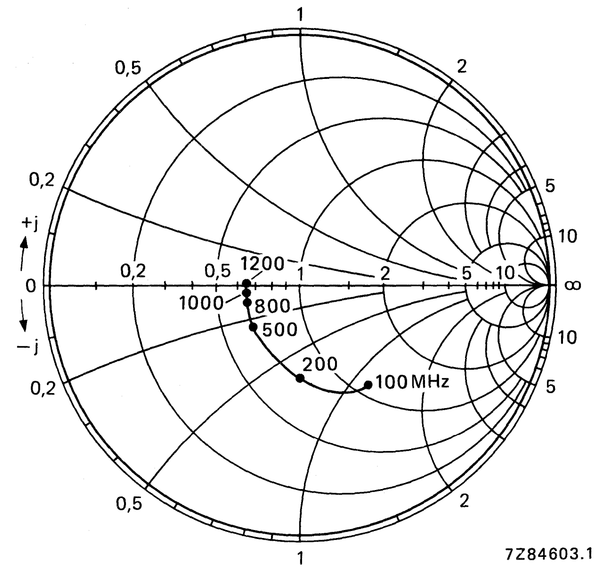


Fig. 3 Input impedance derived from input reflection coefficient s_{ie} co-ordinates in ohm x 50.
V_{CE} = 10 V; I_C = 14 mA; T_{amb} = 25 °C; typical values.

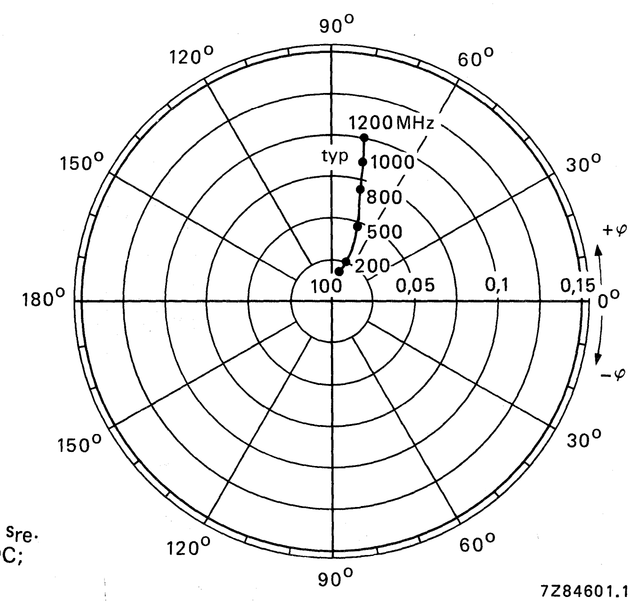


Fig. 4 Reverse transmission coefficient s_{re}.
V_{CE} = 10 V; I_C = 14 mA; T_{amb} = 25 °C; typical values.

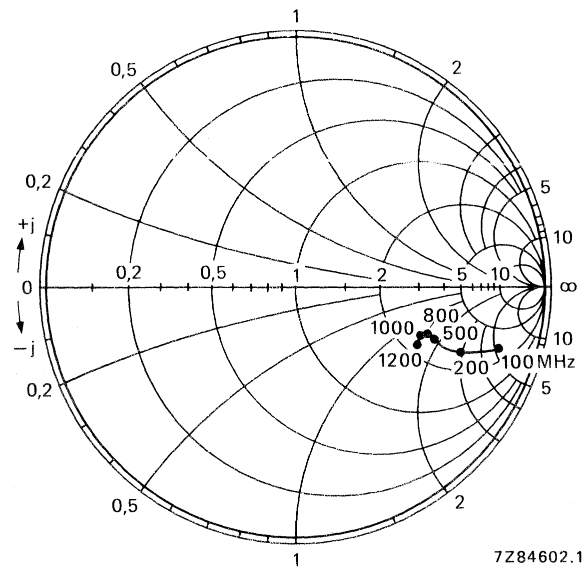


Fig. 5 Output impedance derived from output reflection coefficient s_{oe} co-ordinates in ohm x 50.
V_{CE} = 10 V; I_C = 14 mA; T_{amb} = 25 °C; typical values.

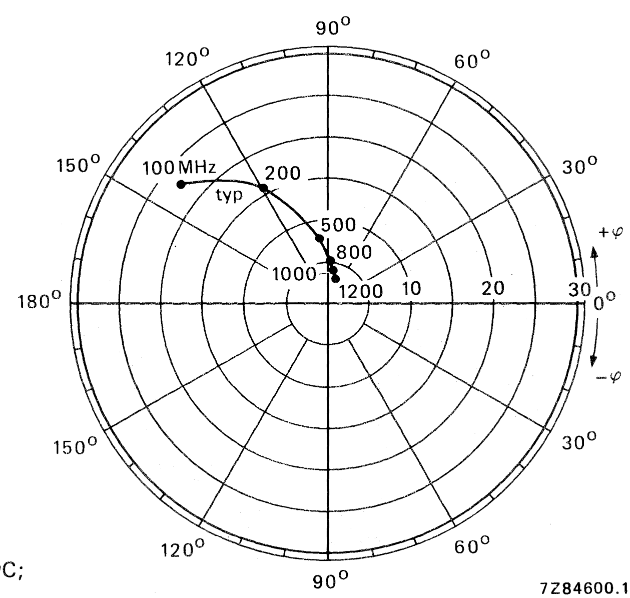


Fig. 6 Forward transmission coefficient s_{fe}.
V_{CE} = 10 V; I_C = 14 mA; T_{amb} = 25 °C; typical values.

s-parameters (common emitter) at V_{CE} = 5 V; T_{amb} = 25 °C; typical values.

I_C mA	f MHz	s_{ie}	s_{re}	s_{fe}	s_{oe}
2	40	0,88/ −8,9°	0,009/83,6°	6,7/174,2°	1,00/ −2,7°
	100	0,86/ −21,9°	0,022/78,3°	6,5/164,2°	0,98/ −6,6°
	200	0,80/ −42,2°	0,041/69,0°	6,0/149,2°	0,94/−12,2°
	500	0,61/ −87,2°	0,073/54,9°	4,2/119,1°	0,81/−20,2°
	800	0,48/−117,4°	0,086/52,7°	3,1/100,5°	0,74/−22,9°
	1000	0,44/−133,8°	0,092/54,2°	2,6/ 91,4°	0,71/−24,2°
	1200	0,41/−147,6°	0,099/57,5°	2,2/ 84,3°	0,70/−25,7°
5	40	0,75/ −14,4°	0,008/81,8°	14,4/170,2°	0,99/ −4,9°
	100	0,70/ −34,0°	0,020/74,2°	13,3/155,3°	0,94/−11,2°
	200	0,60/ −61,7°	0,034/65,0°	10,9/135,8°	0,84/−17,9°
	500	0,40/−111,1°	0,057/61,1°	6,2/106,9°	0,67/−21,9°
	800	0,32/−139,7°	0,074/65,5°	4,2/ 92,4°	0,62/−22,2°
	1000	0,30/−153,2°	0,086/68,2°	3,4/ 85,3°	0,61/−22,8°
	1200	0,29/−166,2°	0,100/70,9°	2,9/ 79,6°	0,60/−24,0°
10	40	0,61/ −21,1°	0,008/79,7°	22,9/165,2°	0,97/ −7,3°
	100	0,54/ −48,5°	0,017/71,4°	19,8/145,8°	0,88/−15,5°
	200	0,42/ −82,1°	0,028/65,2°	14,4/124,7°	0,74/−20,8°
	500	0,30/−132,3°	0,050/69,0°	7,1/ 99,6°	0,59/−20,5°
	800	0,26/−158,0°	0,072/73,7°	4,7/ 87,8°	0,56/−20,3°
	1000	0,25/−168,3°	0,088/75,2°	3,8/ 82,2°	0,56/−20,9°
	1200	0,25/−179,3°	0,104/76,6°	3,2/ 77,5°	0,55/−22,1°
14	40	0,53/ −26,0°	0,007/78,6°	27,7/162,4°	0,96/ −8,7°
	100	0,45/ −58,1°	0,016/70,5°	22,6/140,7°	0,85/−17,2°
	200	0,36/ −94,4°	0,025/66,6°	15,6/119,7°	0,70/−21,0°
	500	0,27/−142,8°	0,049/72,5°	7,3/ 96,9°	0,57/−19,1°
	800	0,25/−166,0°	0,072/76,5°	4,7/ 86,1°	0,55/−19,1°
	1000	0,24/−174,8°	0,088/77,4°	3,8/ 80,5°	0,55/−19,9°
	1200	0,24/ 174,8°	0,105/78,4°	3,2/ 76,2°	0,54/−21,3°
20	40	0,45/ −33,1°	0,007/77,0°	32,3/158,8°	0,94/−10,1°
	100	0,38/ −71,8°	0,015/69,5°	24,7/135,0°	0,80/−18,4°
	200	0,31/−110,6°	0,023/68,3°	16,0/114,6°	0,66/−20,1°
	500	0,26/−154,5°	0,047/75,5°	7,2/ 94,3°	0,56/−17,3°
	800	0,25/−174,2°	0,071/78,7°	4,7/ 84,3°	0,55/−17,8°
	1000	0,25/ 178,5°	0,088/79,3°	3,7/ 79,1°	0,54/−18,9°
	1200	0,26/ 169,9°	0,104/80,0°	3,2/ 74,9°	0,54/−20,5°

s-parameters (common emitter) at V_{CE} = 10 V; T_{amb} = 25 °C; typical values.

I_C mA	f MHz	s_{ie}	s_{re}	s_{fe}	s_{oe}
2	40	0,89/ −8,7°	0,008/83,6°	6,8/174,4°	1,00/ −2,5°
	100	0,86/ −21,2°	0,021/78,5°	6,5/164,6°	0,98/ −6,1°
	200	0,80/ −40,9°	0,038/69,5°	6,0/149,6°	0,94/−11,3°
	500	0,61/ −85,3°	0,069/55,8°	4,3/119,8°	0,82/−18,7°
	800	0,48/−115,4°	0,081/53,8°	3,1/101,2°	0,75/−21,3°
	1000	0,44/−131,4°	0,086/55,5°	2,6/ 92,1°	0,73/−22,5°
	1200	0,40/−145,6°	0,093/58,9°	2,2/ 85,0°	0,72/−23,9°
5	40	0,77/ −13,6°	0,008/81,8°	14,2/170,5°	0,99/ −4,5°
	100	0,73/ −32,3°	0,019/74,7°	13,2/155,8°	0,95/−10,3°
	200	0,62/ −58,8°	0,032/65,6°	11,0/136,8°	0,85/−16,6°
	500	0,41/−107,2°	0,054/61,4°	6,3/107,7°	0,69/−20,4°
	800	0,32/−135,9°	0,071/65,9°	4,2/ 92,9°	0,64/−20,8°
	1000	0,30/−150,0°	0,082/68,6°	3,5/ 86,1°	0,63/−21,3°
	1200	0,28/−162,9°	0,095/71,5°	2,9/ 80,5°	0,62/−22,4°
10	40	0,66/ −19,4°	0,007/80,1°	22,5/165,9°	0,97/ −6,6°
	100	0,58/ −44,7°	0,017/71,8°	19,5/147,0°	0,90/−14,1°
	200	0,45/ −76,2°	0,027/65,4°	14,5/126,0°	0,76/−19,3°
	500	0,29/−125,1°	0,049/68,7°	7,2/100,6°	0,62/−19,2°
	800	0,24/−151,8°	0,070/73,5°	4,7/ 88,8°	0,59/−19,0°
	1000	0,24/−162,9°	0,084/75,2°	3,8/ 82,6°	0,58/−19,7°
	1200	0,23/−174,8°	0,099/76,8°	3,2/ 78,3°	0,58/−20,9°
14	40	0,60/ −23,2°	0,007/78,6°	27,2/163,0°	0,96/ −7,9°
	100	0,51/ −52,5°	0,016/70,6°	22,6/141,8°	0,86/−15,8°
	200	0,38/ −86,2°	0,025/66,4°	15,7/120,7°	0,72/−19,6°
	500	0,26/−134,3°	0,047/72,0°	7,5/ 97,8°	0,60/−18,0°
	800	0,22/−159,3°	0,069/76,2°	4,8/ 86,8°	0,57/−18,0°
	1000	0,22/−169,0°	0,085/77,3°	3,9/ 81,3°	0,57/−18,7°
	1200	0,22/ 179,8°	0,100/78,5°	3,3/ 76,8°	0,57/−20,1°
20	40	0,54/ −28,2°	0,007/77,4°	31,7/159,9°	0,95/ −9,1°
	100	0,45/ −61,7°	0,015/69,5°	24,7/136,8°	0,82/−16,8°
	200	0,33/ −97,5°	0,023/67,5°	16,3/116,2°	0,68/−18,8°
	500	0,24/−143,7°	0,046/74,4°	7,4/ 95,3°	0,59/−16,4°
	800	0,22/−166,4°	0,069/78,0°	4,8/ 85,2°	0,57/−16,9°
	1000	0,22/−174,7°	0,084/78,7°	3,8/ 80,1°	0,57/−17,8°
	1200	0,22/ 176,3°	0,100/79,7°	3,3/ 76,0°	0,57/−19,4°

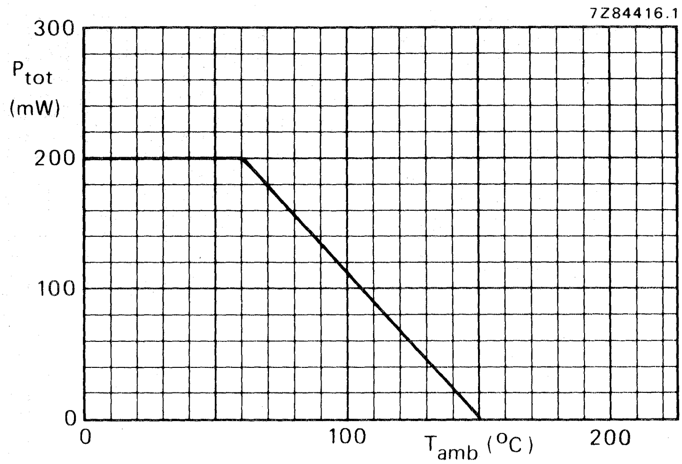


Fig. 7 Power derating curve.

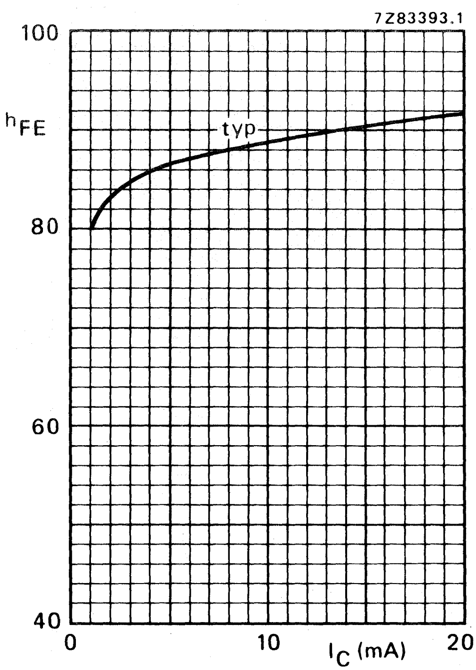


Fig. 8 V_{CE} = 10 V; T_j = 25 ^oC; typical values.

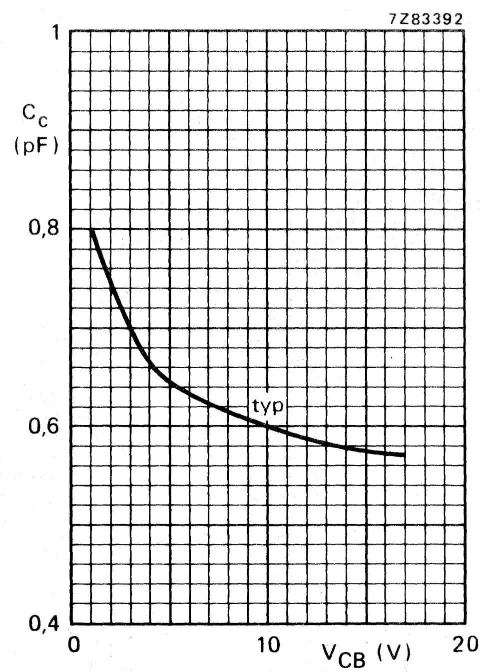


Fig. 9 $I_E = I_e = 0$; f = 1 MHz; T_j = 25 ^oC; typical values.

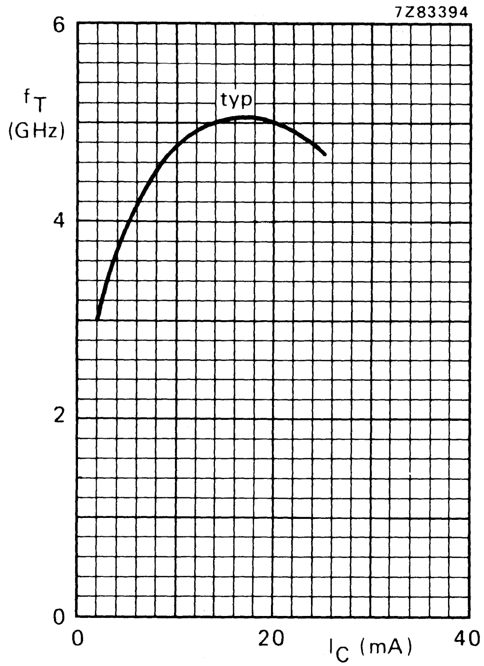


Fig. 10 V_{CE} = 10 V; f = 500 MHz; T_j = 25 °C; typical values.

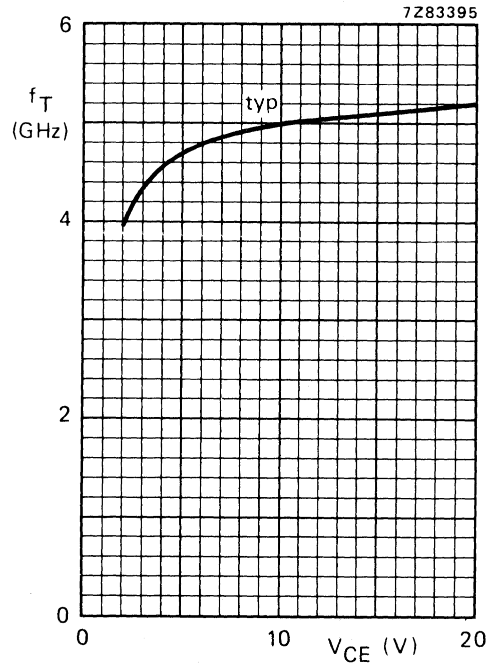


Fig. 11 I_C = 14 mA; f = 500 MHz; T_j = 25 °C; typical values.

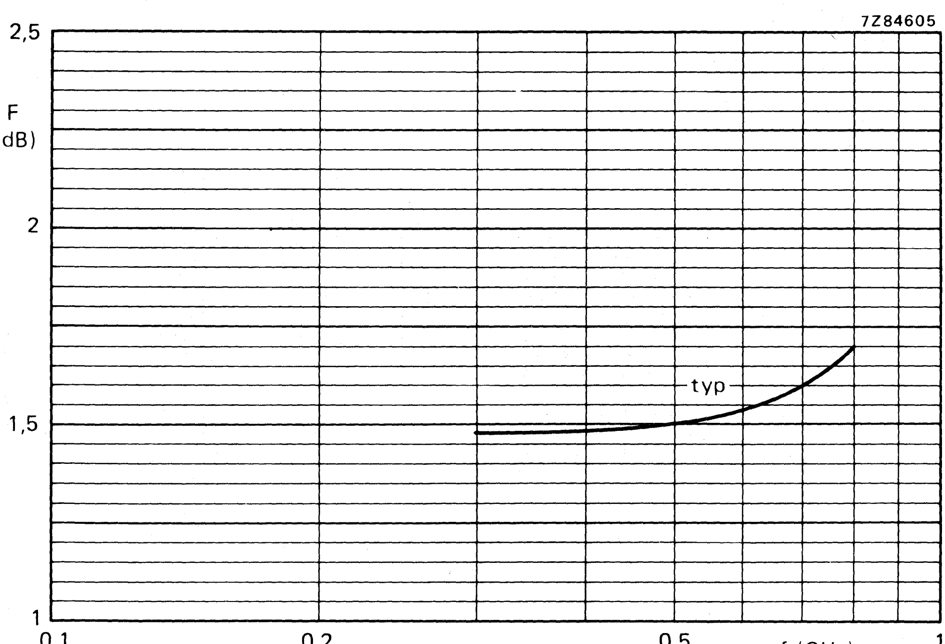


Fig. 12 V_{CE} = 10 V; I_C = 4 mA; Z_S = optimum; T_{amb} = 25 °C; typical values.

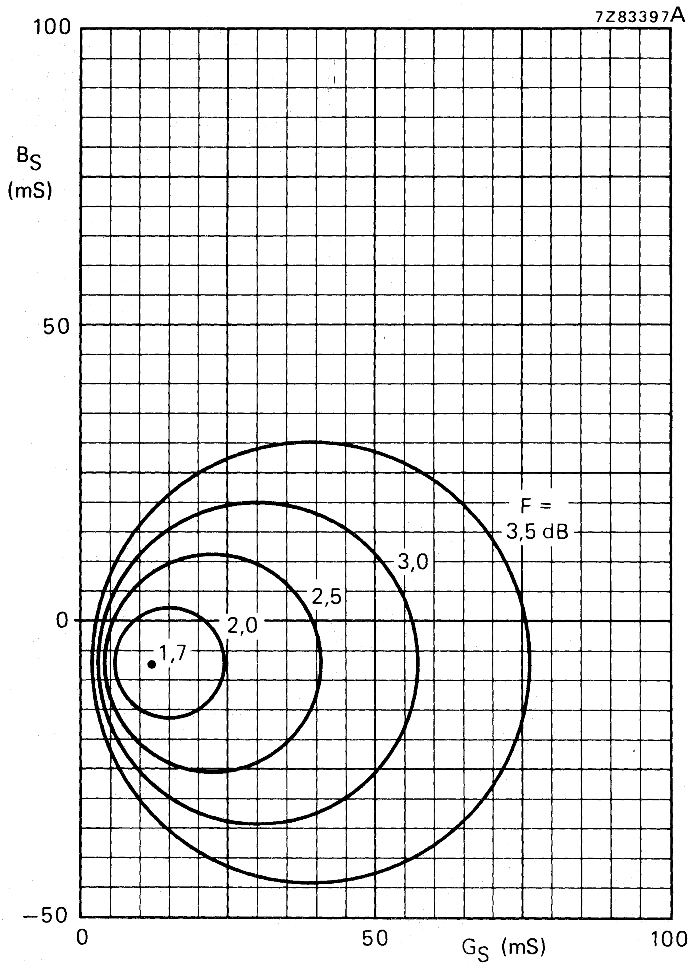


Fig. 13 Circles of constant noise figure.
V_{CE} = 10 V; I_C = 4 mA; f = 800 MHz; T_{amb} = 25 °C;
typical values.

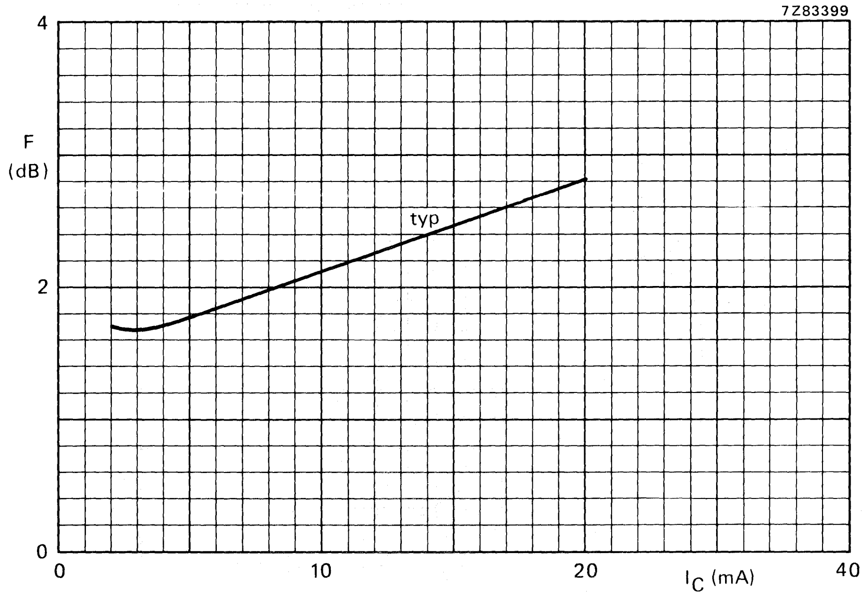


Fig. 14 V_{CE} = 10 V; f = 800 MHz; Z_S = optimum; T_{amb} = 25 °C; typical values.

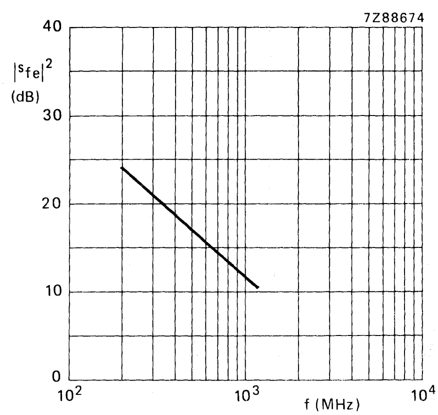


Fig. 15 V_{CE} = 10 V; I_C = 14 mA; T_{amb} = 25 °C; typical values.

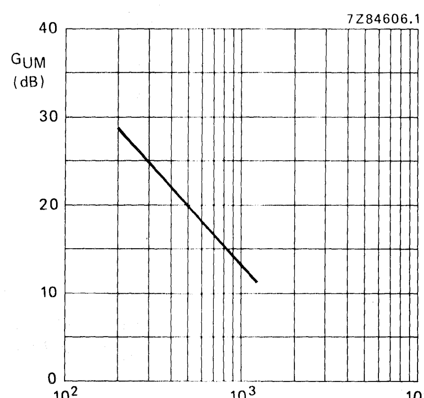


Fig. 16 V_{CE} = 10 V; I_C = 14 mA; T_{amb} = 25 °C; typical values.

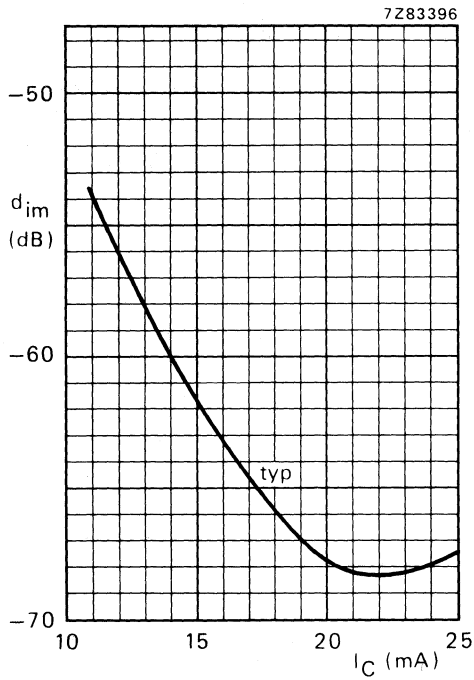


Fig. 17 V_{CE} = 10 V; V_o = 43,5 dBmV = 150 mV; $f_{(p+q-r)}$ = 793,25 MHz; T_{amb} = 25 °C; measured in MATV test circuit (see Fig. 2); typical values.

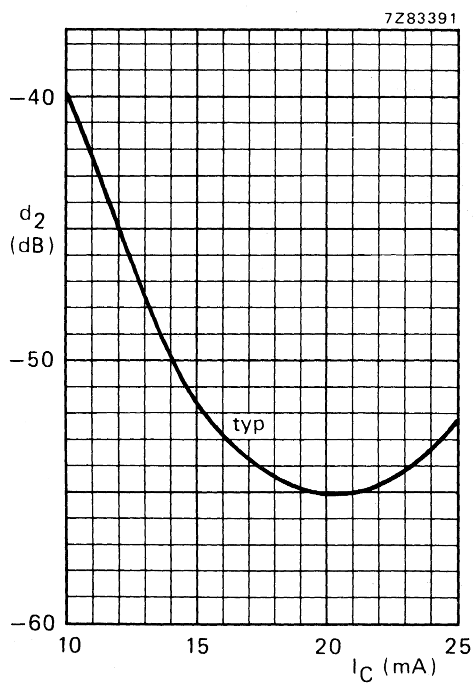


Fig. 18 V_{CE} = 10 V; V_o = 60 mV; $f_{(p+q)}$ = 810 MHz; T_{amb} = 25 °C; measured in MATV test circuit (see Fig. 2); typical values.

N-P-N 1 GHz WIDEBAND TRANSISTOR

N-P-N transistor in a SOT-23 plastic envelope. It is primarily intended for use in u.h.f. and microwave amplifiers in thick and thin-film circuits, such as in aerial amplifiers, radar systems, oscilloscopes, spectrum analysers etc. The transistor features very low intermodulation distortion and high power gain; thanks to its very high transition frequency, it also has excellent wideband properties and low noise up to high frequencies.

P-N-P complement is the BFT93.

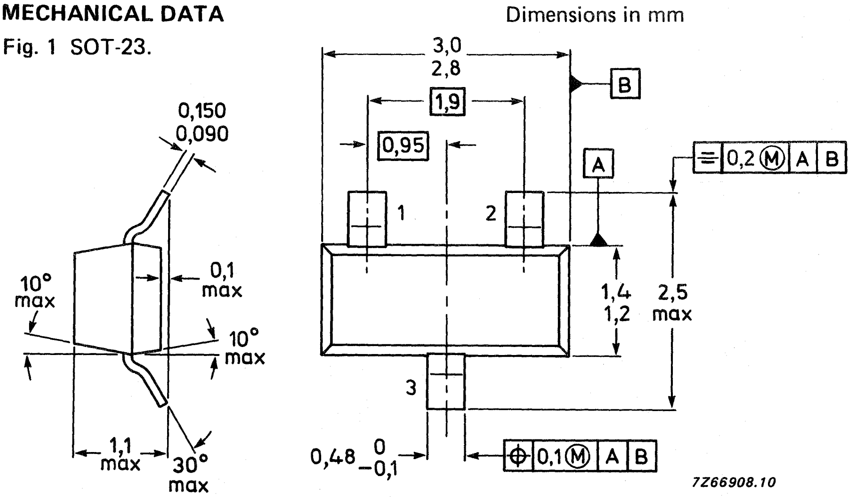
QUICK REFERENCE DATA

Collector-base voltage (open emitter)	V_{CBO}	max.	15	V
Collector-emitter voltage (open base)	V_{CEO}	max.	12	V
Collector current (d.c.)	I_C	max.	35	mA
Total power dissipation up to T_{amb} = 60 °C	P_{tot}	max.	200	mW
Junction temperature	T_j	max.	150	°C
Transition frequency at f = 500 MHz I_C = 30 mA; V_{CE} = 5 V	f_T	typ.	5	GHz
Feedback capacitance at f = 1 MHz I_C = 2 mA; V_{CE} = 5 V	C_{re}	typ.	0,8	pF
Noise figure at optimum source impedance I_C = 2 mA; V_{CE} = 5 V; f = 500 MHz;	F	typ.	1,9	dB
Max. unilateral power gain I_C = 30 mA; V_{CE} = 5 V; f = 500 MHz;	G_{UM}	typ.	16,5	dB
Intermodulation distortion at T_{amb} = 25 °C I_C = 30 mA; V_{CE} = 5 V; R_L = 75 Ω; V_o = 300 mV $f_{(p+q-r)}$ = 493,25 MHz	d_{im}	typ.	−60	dB

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-23.

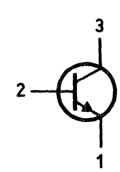


TOP VIEW

If required, the R-version (reverse pinning) is available on request.

Marking code

BFR93 = R1



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	V_{CBO}	max.	15 V
Collector-emitter voltage (open base)	V_{CEO}	max.	12 V
Emitter-base voltage (open collector)	V_{EBO}	max.	2,0 V
Collector current (d.c.)	I_C	max.	35 mA
Total power dissipation up to T_{amb} = 60 °C**	P_{tot}	max.	200 mW
Storage temperature	T_{stg}	−65 to + 150 °C	
Junction temperature	T_j	max.	150 °C

THERMAL CHARACTERISTICS *

$T_j = P \times (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	60 K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280 K/W
From soldering points to ambient **	$R_{th\ s\text{-}a}$	=	90 K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current $I_E = 0$; V_{CB} = 10 V	I_{CBO}	max.	50 nA
D.C. current gain ▲ I_C = 30 mA; V_{CE} = 5 V	h_{FE}	min. typ.	25 50
Transition frequency at f = 500 MHz ▲ I_C = 30 mA; V_{CE} = 5 V	f_T	typ.	5 GHz
Collector capacitance at f = 1 MHz $I_E = I_e = 0$; V_{CB} = 10 V	C_c	typ.	0,7 pF
Emitter capacitance at f = 1 MHz $I_C = I_c = 0$; V_{EB} = 0,5 V	C_e	typ.	1,8 pF
Feedback capacitance at f = 1 MHz I_C = 2 mA; V_{CE} = 5 V; T_{amb} = 25 °C	C_{re}	typ.	0,8 pF

▲ Measured under pulse conditions.
* See *Thermal characteristics.*
** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

Noise figure at optimum source impedance *			
$I_C = 2$ mA; $V_{CE} = 5$ V; f = 500 MHz; $T_{amb} = 25$ °C	F	typ.	1,9 dB
Max. unilateral power gain (s_{re} assumed to be zero)			

$$G_{UM} = 10 \log \frac{|s_{fe}|^2}{(1 - |s_{ie}|^2)(1 - |s_{oe}|^2)}$$

$I_C = 30$ mA; $V_{CE} = 5$ V; f = 500 MHz; $T_{amb} = 25$ °C	G_{UM}	typ.	16,5 dB
Intermodulation distortion at $T_{amb} = 25$ °C *			
$I_C = 30$ mA; $V_{CE} = 5$ V; $R_L = 75\ \Omega$; V.S.W.R. < 2			
$V_p = V_o = 300$ mV at $f_p = 495{,}25$ MHz			
$V_q = V_o - 6$ dB at $f_q = 503{,}25$ MHz			
$V_r = V_o - 6$ dB at $f_r = 505{,}25$ MHz			
Measured at $f_{(p+q-r)} = 493{,}25$ MHz	d_{im}	typ.	−60 dB

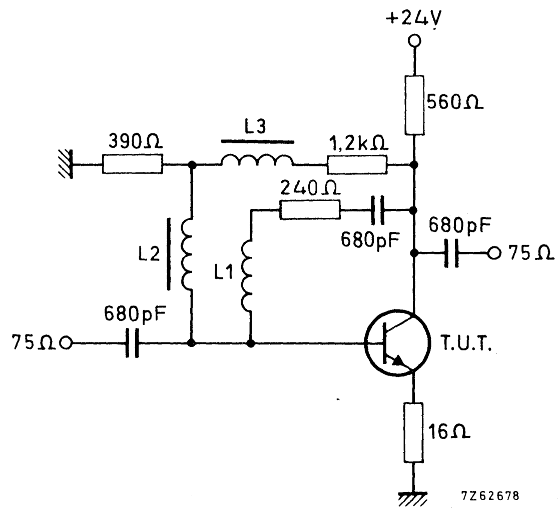


Fig. 2 Intermodulation test circuit.

L1 = 4 turns Cu wire (0,35); winding pitch 1 mm; int. dia. 4 mm
L2 and L3 5 μH (code number: 3122 108 20150)

* Crystal mounted in a BFR91 envelope.

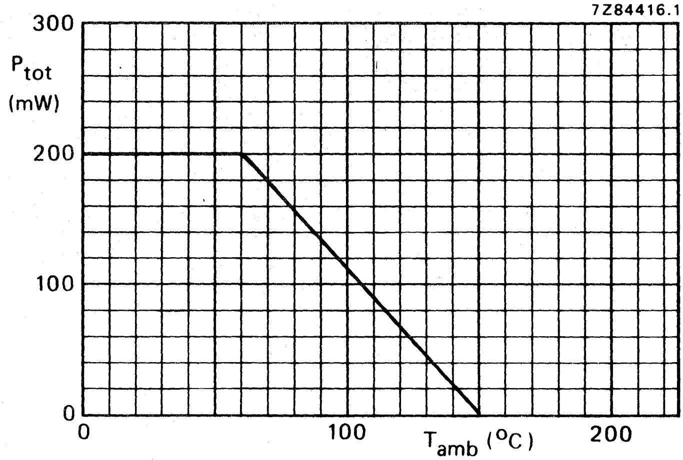


Fig. 3 Power derating curve.

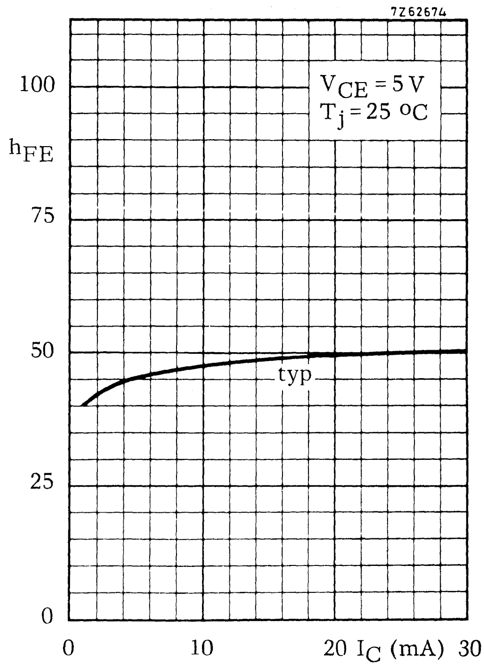


Fig. 4.

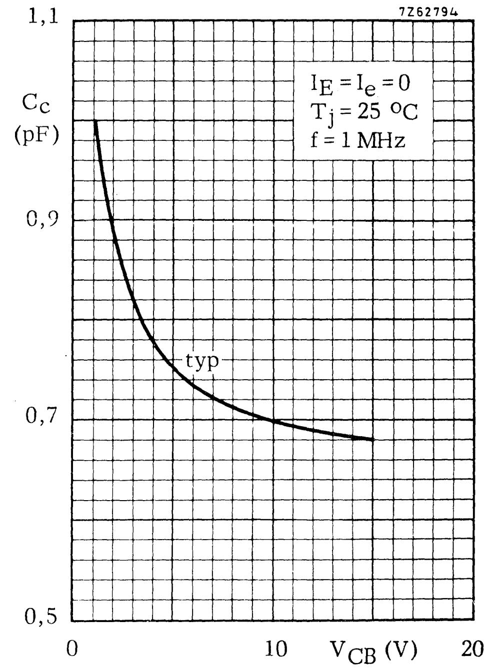


Fig. 5.

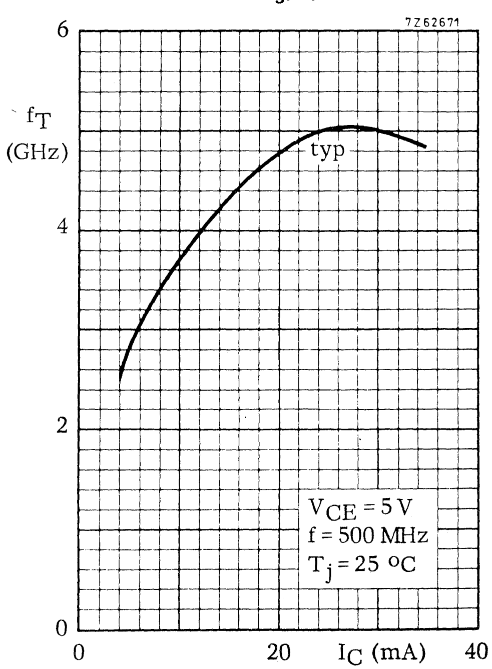


Fig. 6.

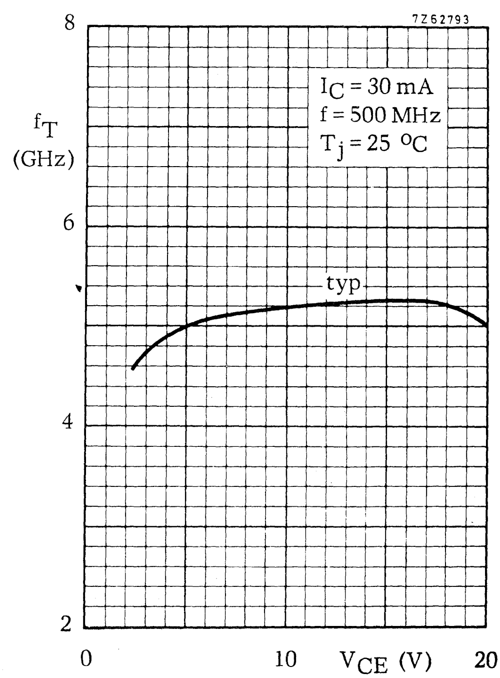


Fig. 7.

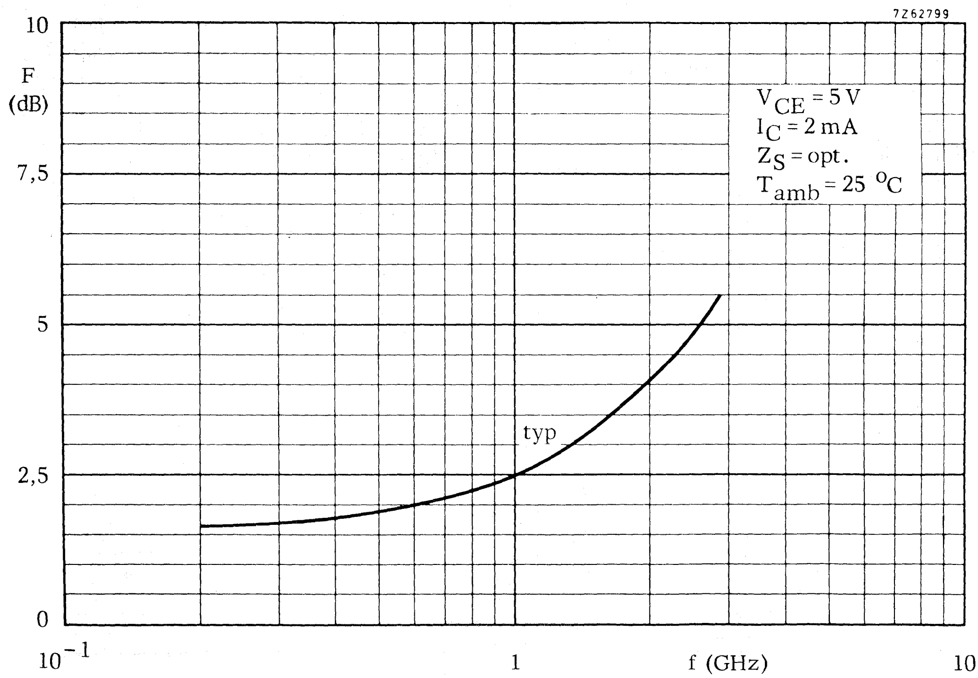

7Z62799
10
F
(dB)
7,5
5
2,5
0
V_{CE} = 5 V
I_C = 2 mA
Z_S = opt.
T_{amb} = 25 °C
typ
10^{-1}
1
f (GHz)
10

Fig. 8.

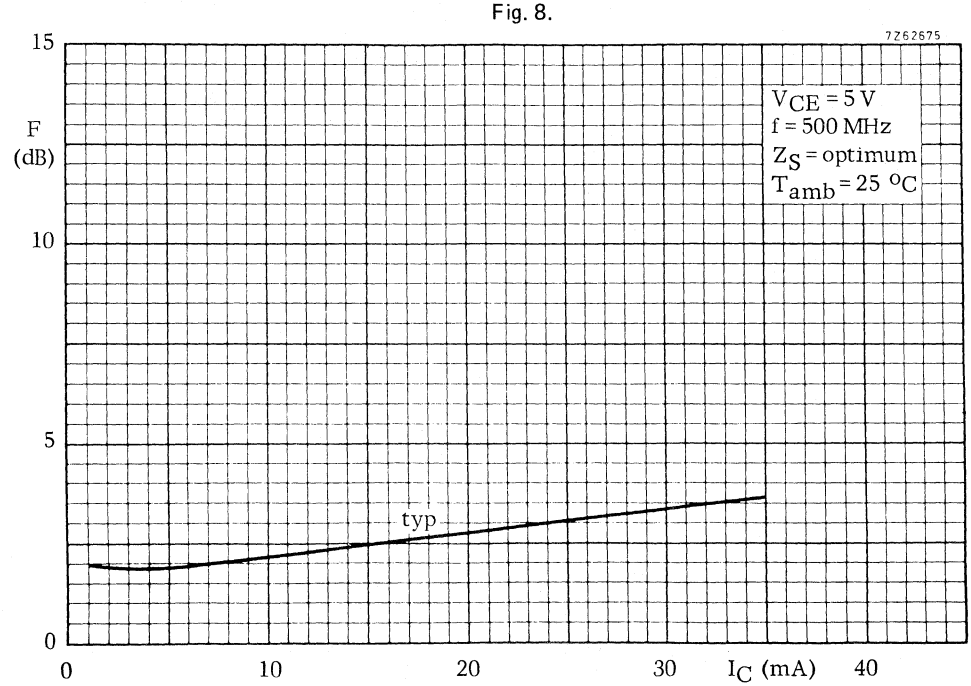

7Z62675
15
F
(dB)
10
5
0
V_{CE} = 5 V
f = 500 MHz
Z_S = optimum
T_{amb} = 25 °C
typ
0
10
20
30
I_C (mA)
40

Fig. 9.

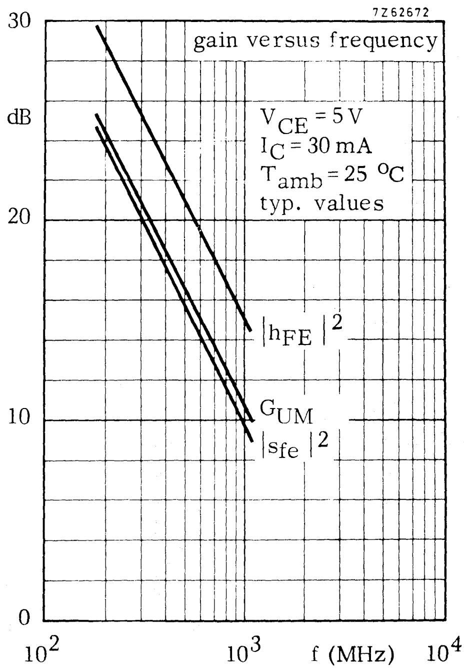

7Z62672
gain versus frequency
30
dB
20
10
0
V_{CE} = 5 V
I_C = 30 mA
T_{amb} = 25 °C
typ. values
$|h_{FE}|^2$
G_{UM}
$|s_{fe}|^2$
10^2
10^3
f (MHz)
10^4

Fig. 10.

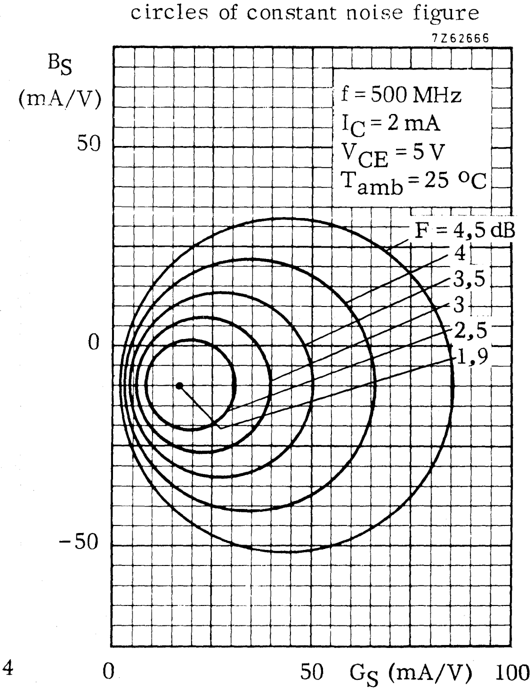

circles of constant noise figure
7Z62666
B_S
(mA/V)
50
0
−50
f = 500 MHz
I_C = 2 mA
V_{CE} = 5 V
T_{amb} = 25 °C
F = 4,5 dB
4
3,5
3
2,5
1,9
0
50
G_S (mA/V)
100

Fig. 11.

V_{CE} = 5 V
I_C = 30 mA
T_{amb} = 25 °C

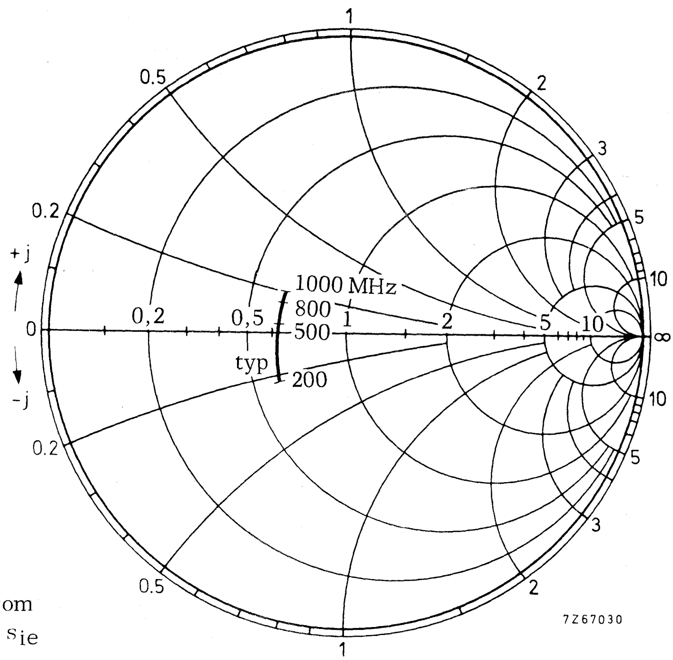


Fig. 12.

Input impedance derived from input reflection coefficient s_{ie} coordinates in ohm x 50

V_{CE} = 5 V
I_C = 30 mA
T_{amb} = 25 °C

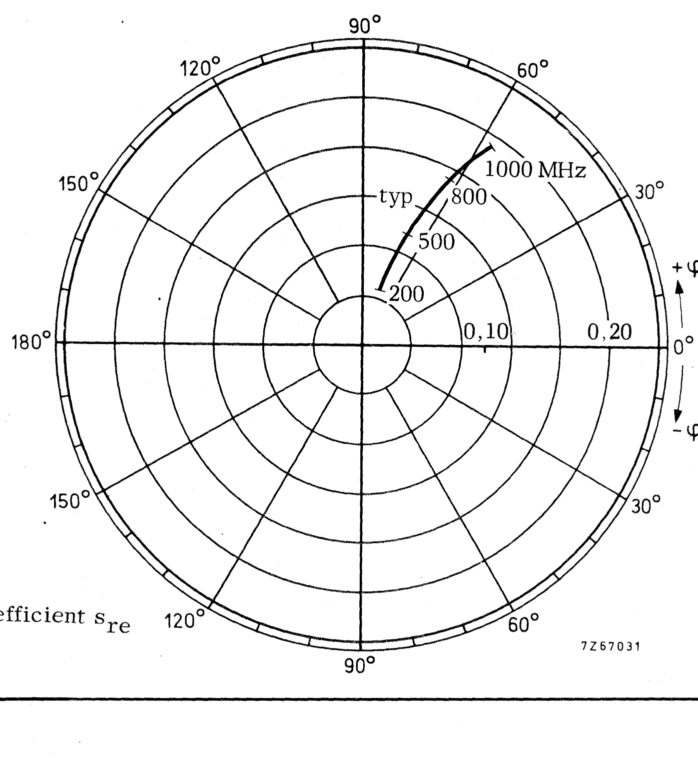


Fig. 13.

Reverse transmission coefficient s_{re}

V_{CE} = 5 V
I_C = 30 mA
T_{amb} = 25 °C

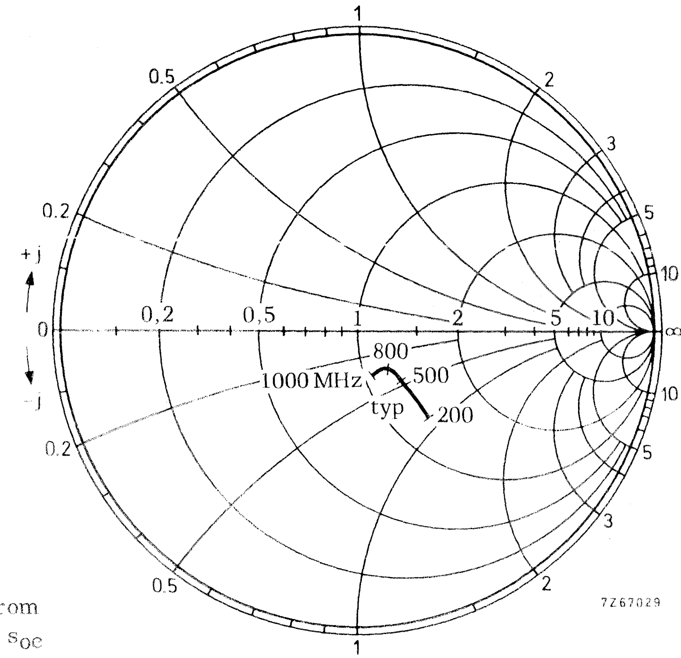


Fig. 14.

Output impedance derived from output reflection coefficient s_{oe} coordinates in ohm x 50

V_{CE} = 5 V
I_C = 30 mA
T_{amb} = 25 °C

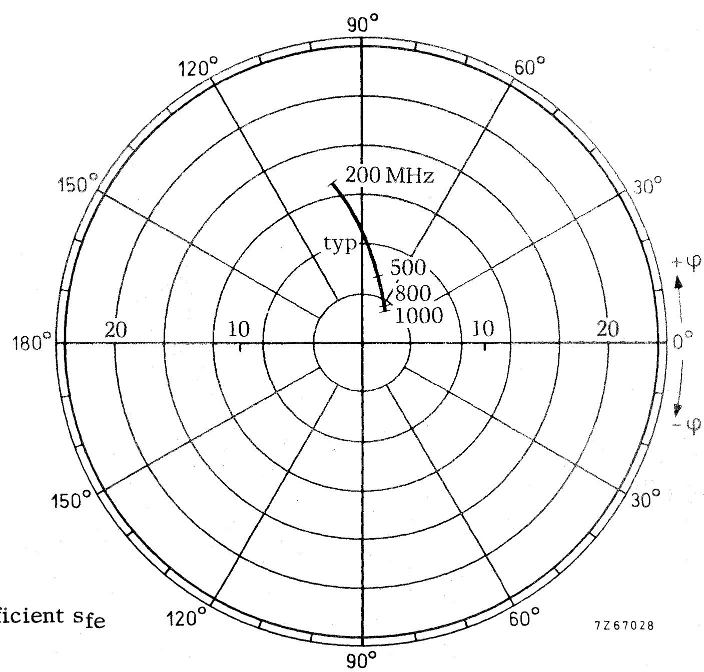


Fig. 15.

Forward transmission coefficient s_{fe}

N-P-N 1 GHz WIDEBAND TRANSISTOR

N-P-N transistors in a SOT-23 plastic envelope. They are primarily intended for use in v.h.f./u.h.f. broadband amplifiers. The transistors feature:

- low noise;
- very low intermodulation distortion;
- high power gain;
- P-N-P complement to the BFR93

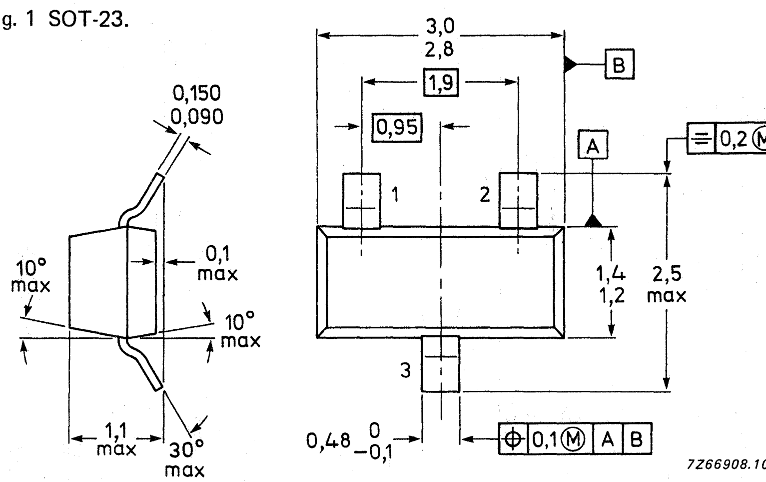
QUICK REFERENCE DATA

Collector-base voltage (open emitter)	V_{CBO}	max.	15	V
Collector-emitter voltage (open base)	V_{CEO}	max.	12	V
Collector current (d.c.)	I_C	max.	35	mA
Total power dissipation up to T_{amb} = 45 °C	P_{tot}	max.	250	mW
Junction temperature	T_j	max.	150	°C
Transition frequency at f = 500 MHz I_C = 30 mA; V_{CE} = 5 V	f_T	typ.	5	GHz
Feedback capacitance at f = 1 MHz I_C = 0; V_{CE} = 5 V; T_{amb} = 25 °C	C_{re}	typ.	0,6	pF
Noise figure at optimum source impedance I_C = 4 mA; V_{CE} = 8 V; f = 800 MHz	F	typ.	1,6	dB
Output voltage at d_{im} = −60 dB I_C = 30 mA; V_{CE} = 8 V; R_L = 75 Ω; T_{amb} = 25 °C $f_{(p+q-r)}$ = 793,25 MHz	V_o	typ.	425	mV

MECHANICAL DATA

Dimensions in mm

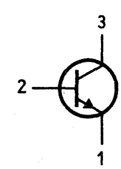
Fig. 1 SOT-23.



TOP VIEW

Marking code

BFR93A = R2



If required, the R-version (reverse pinning) is available on request
See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	V_{CBO}	max.	15 V
Collector-emitter voltage (open base)	V_{CEO}	max.	12 V
Emitter-base voltage (open collector)	V_{EBO}	max.	2,0 V
Collector current (d.c.)	I_C	max.	35 mA
Total power dissipation up to T_{amb} = 45 °C**	P_{tot}	max.	250 mW
Storage temperature	T_{stg}	−65 to + 150 °C	
Junction temperature	T_j	max.	150 °C

THERMAL CHARACTERISTICS*

$T_j = P \times (R_{th\,j\text{-}t} + R_{th\,t\text{-}s} + R_{th\,s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\,j\text{-}t}$	=	60 K/W
From tab to soldering points	$R_{th\,t\text{-}s}$	=	280 K/W
From soldering points to ambient**	$R_{th\,s\text{-}a}$	=	90 K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current $I_E = 0$; $V_{CB} = 5$ V	I_{CBO}	max.	50 nA
D.C. current gain▲ $I_C = 30$ mA; $V_{CE} = 5$ V	h_{FE}	min. typ.	40 90
Transition frequency at f = 500 MHz▲ $I_C = 30$ mA; $V_{CE} = 5$ V	f_T	typ.	5 GHz
Collector capacitance at f = 1 MHz $I_E = I_e = 0$; $V_{CB} = 5$ V	C_c	typ.	0,7 pF
Emitter capacitance at f = 1 MHz $I_C = I_c = 0$; $V_{EB} = 0{,}5$ V	C_e	typ.	1,9 pF
Feedback capacitance at f = 1 MHz $I_C = 0$; $V_{CE} = 5$ V; $T_{amb} = 25$ °C	C_{re}	typ.	0,6 pF
Noise figure at optimum source impedance▲ $I_C = 4$ mA; $V_{CE} = 8$ V; f = 800 MHz $I_C = 30$ mA; $V_{CE} = 8$ V; f = 800 MHz	F F	typ. typ.	1,6 dB 2,3 dB

Maximum unilateral power gain (s_{re} assumed to be zero)
See Figs 10 to 15

$$G_{UM}\ (\text{in dB}) = 10 \log \frac{|s_{fe}|^2}{(1 - |s_{ie}|^2)(1 - |s_{oe}|^2)}$$

$I_C = 30$ mA; $V_{CE} = 8$ V; f = 800 MHz; $T_{amb} = 25$ °C	G_{UM}	typ.	14 dB

▲ Measured under pulse conditions.
* See *Thermal characteristics.*
** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

Output voltage at d_{im} = –60 dB (see Figs 2 and 16)*			
(DIN 45004B, par. 6.3: 3-tone)			
I_C = 30 mA; V_{CE} = 8 V; R_L = 75 Ω; T_{amb} = 25 °C			
$V_p = V_o$ at d_{im} = –60 dB; f_p = 795,25 MHz			
$V_q = V_o$ –6 dB ; f_q = 803,25 MHz			
$V_r = V_o$ –6 dB ; f_r = 805,25 MHz			
Measured at $f_{(p+q-r)}$ = 793,25 MHz	V_o	typ.	425 mV
Second harmonic distortion (see Figs 2 and 17)*			
I_C = 30 mA; V_{CE} = 8 V; R_L = 75 Ω; T_{amb} = 25 °C			
V_p = 200 mV at f_p = 250 MHz			
V_q = 200 mV at f_q = 560 MHz			
measured at $f_{(p+q)}$ = 810 MHz	d_2	typ.	–50 dB

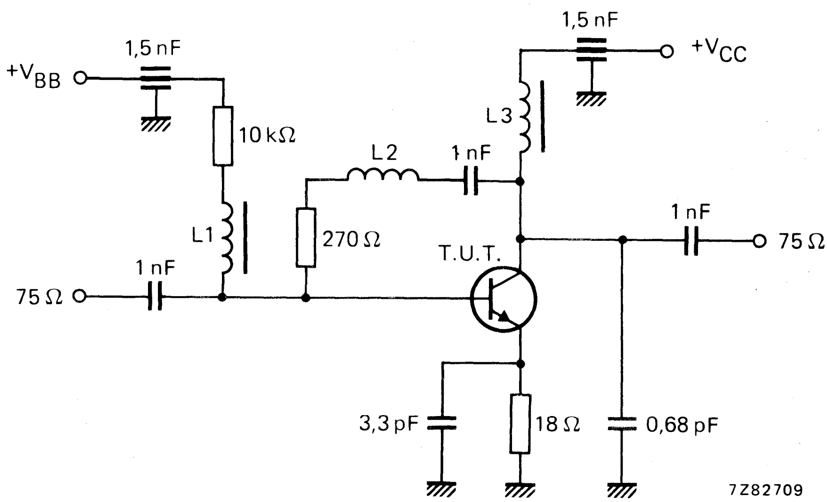


Fig. 2 Intermodulation distortion and second harmonic distortion MATV test circuit.

L1 = L3 = 5 μH micro choke
L2 = 3 turns Cu wire (0,4 mm); internal diameter 3 mm; winding pitch 1 mm.

* Measured on same crystal in a SOT-37 envelope (BFR91A).

s-parameters (common emitter)

V_{CE} V	I_C mA	f MHz	s_{ie}	s_{re}	s_{fe}	s_{oe}
		40	0,89/ −12,4°	0,016/82,3°	7,0/171,8°	0,88/ −4,8°
		100	0,87/ −30,1°	0,038/74,2°	6,7/160,1°	0,96/−11,3°
		200	0,80/ −56,3°	0,067/61,8°	6,0/142,3°	0,88/−20,1°
5	2	500	0,64/−109,5°	0,106/44,3°	3,8/110,6°	0,69/−31,9°
		800	0,57/−140,3°	0,116/41,8°	2,7/ 91,5°	0,60/−35,5°
		1000	0,54/−154,5°	0,119/43,9°	2,2/ 82,8°	0,58/−38,0°
		1200	0,53/−166,6°	0,124/48,2°	1,9/ 75,1°	0,56/−40,2°
		40	0,77/ −19,9°	0,015/79,4°	15,1/166,8°	0,97/ −8,8°
		100	0,72/ −46,9°	0,033/68,6°	13,5/149,7°	0,89/−19,6°
		200	0,62/ −81,4°	0,053/57,0°	10,5/128,5°	0,73/−30,3°
5	5	500	0,48/−134,4°	0,079/52,6°	5,5/100,5°	0,51/−37,3°
		800	0,45/−159,8°	0,099/57,8°	3,6/ 85,6°	0,44/−37,9°
		1000	0,44/−170,8°	0,114/61,0°	3,0/ 78,8°	0,42/−39,3°
		1200	0,43/ 179,8°	0,131/64,2°	2,5/ 72,9°	0,41/−40,9°
		40	0,63/ −29,7°	0,013/76,5°	24,4/161,0°	0,95/−13,5°
		100	0,56/ −66,2°	0,028/64,8°	20,0/139,4°	0,80/−17,8°
		200	0,47/−105,4°	0,042/57,8°	13,6/118,0°	0,59/−37,3°
5	10	500	0,41/−152,0°	0,070/62,6°	6,4/ 94,8°	0,39/−39,0°
		800	0,39/−171,7°	0,099/67,6°	4,1/ 82,7°	0,35/−38,2°
		1000	0,39/ 179,6°	0,119/69,1°	3,4/ 76,7°	0,34/−39,1°
		1200	0,39/ 171,6°	0,140/70,5°	2,8/ 71,5°	0,33/−40,7°
		40	0,47/ −44,2°	0,012/73,8°	35,2/154,0°	0,90/−19,2°
		100	0,42/ −90,7°	0,023/63,9°	25,4/129,3°	0,68/−35,0°
		200	0,39/−129,4°	0,034/62,9°	15,6/109,7°	0,47/−41,0°
5	20	500	0,37/−165,1°	0,067/70,5°	6,8/ 90,9°	0,32/−38,4°
		800	0,37/ 179,5°	0,101/73,2°	4,4/ 80,3°	0,29/−37,4°
		1000	0,36/ 173,0°	0,124/73,4°	3,6/ 75,4°	0,29/−38,3°
		1200	0,37/ 166,2°	0,148/73,6°	3,0/ 70,3°	0,28/−40,0°
		40	0,39/ −56,3°	0,011/72,3°	40,8/149,5°	0,86/−22,5°
		100	0,38/−106,8°	0,021/64,5°	27,4/124,0°	0,61/−37,9°
		200	0,37/−141,6°	0,032/66,4°	16,0/105,8°	0,41/−41,1°
5	30	500	0,37/−171,0°	0,067/73,5°	6,9/ 88,9°	0,29/−36,6°
		800	0,37/ 175,9°	0,102/75,2°	4,4/ 79,1°	0,27/−36,0°
		1000	0,36/ 170,0°	0,126/74,8°	3,6/ 74,2°	0,27/−37,1°
		1200	0,37/ 163,9°	0,150/74,6°	3,0/ 69,5°	0,27/−39,0°

s-parameters (common emitter)

V_{CE} V	I_C mA	f MHz	s_{ie}	s_{re}	s_{fe}	s_{oe}
		40	0,90/ −12,2°	0,015/82,1°	6,9/171,7°	0,99/ −4,8°
		100	0,88/ −29,2°	0,036/74,5°	6,6/160,4°	0,96/−10,8°
		200	0,81/ −54,7°	0,064/62,4°	5,9/143,1°	0,89/−19,2°
8	2	500	0,64/−107,0°	0,103/44,9°	3,8/111,5°	0,71/−30,6°
		800	0,56/−138,1°	0,112/42,1°	2,7/ 92,2°	0,62/−34,1°
		1000	0,54/−152,6°	0,116/44,1°	2,3/ 83,6°	0,60/−36,4°
		1200	0,52/−165,2°	0,120/48,5°	1,9/ 75,9°	0,58/−38,6°
		40	0,78/ −19,2°	0,014/79,4°	14,8/166,9°	0,98/ −8,6°
		100	0,73/ −44,6°	0,032/69,0°	13,5/150,4°	0,90/−18,7°
		200	0,63/ −78,1°	0,051/57,5°	10,5/129,4°	0,75/−28,9°
8	5	500	0,48/−131,2°	0,077/52,5°	5,6/101,3°	0,53/−35,7°
		800	0,44/−157,3°	0,096/57,7°	3,7/ 86,3°	0,46/−36,2°
		1000	0,42/−168,3°	0,110/61,0°	3,0/ 79,5°	0,44/−37,5°
		1200	0,42/−178,3°	0,126/64,3°	2,6/ 73,6°	0,43/−39,0°
		40	0,66/ −27,7°	0,013/76,7°	24,0/161,5°	0,95/−12,9°
		100	0,58/ −62,0°	0,027/65,4°	19,9/140,4°	0,81/−26,3°
		200	0,48/−100,1°	0,041/58,0°	13,8/119,0°	0,61/−35,5°
8	10	500	0,40/−148,2°	0,068/62,2°	6,5/ 95,4°	0,42/−37,0°
		800	0,38/−169,1°	0,096/67,4°	4,2/ 83,0°	0,37/−36,2°
		1000	0,37/−178,3°	0,116/69,0°	3,4/ 77,4°	0,36/−37,0°
		1200	0,37/ 173,6°	0,136/70,5°	2,9/ 72,5°	0,35/−38,5°
		40	0,53/ −39,6°	0,012/73,8°	34,7/154,8°	0,91/−18,1°
		100	0,45/ −83,0°	0,023/63,9°	25,6/130,5°	0,70/−33,2°
		200	0,39/−122,0°	0,034/62,2°	15,9/110,6°	0,49/−39,0°
8	20	500	0,35/−161,3°	0,066/69,7°	7,0/ 91,4°	0,34/−36,2°
		800	0,35/−177,9°	0,098/72,7°	4,5/ 80,7°	0,31/−35,1°
		1000	0,34/ 175,2°	0,121/73,1°	3,7/ 75,8°	0,31/−36,0°
		1200	0,34/ 168,3°	0,143/73,4°	3,1/ 71,2°	0,30/−37,5°
		40	0,47/ −48,0°	0,011/72,2°	40,3/150,8°	0,87/−20,9°
		100	0,41/ −95,5°	0,021/63,8°	27,5/125,4°	0,63/−35,7°
		200	0,36/−132,8°	0,032/64,9°	16,4/106,8°	0,44/−38,9°
8	30	500	0,35/−166,6°	0,065/72,3°	7,1/ 89,6°	0,32/−34,4°
		800	0,34/ 178,8°	0,100/74,4°	4,5/ 79,7°	0,30/−33,6°
		1000	0,34/ 172,7°	0,122/74,4°	3,7/ 74,7°	0,30/−34,7°
		1200	0,34/ 166,0°	0,145/74,3°	3,1/ 70,3°	0,29/−36,5°

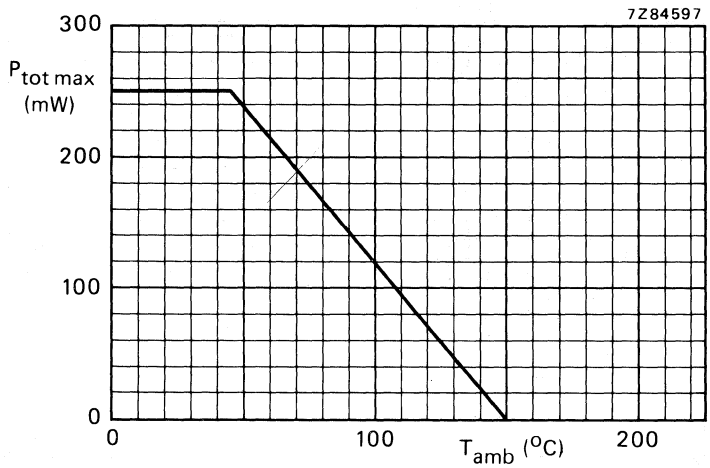


Fig. 3 Power derating curve.

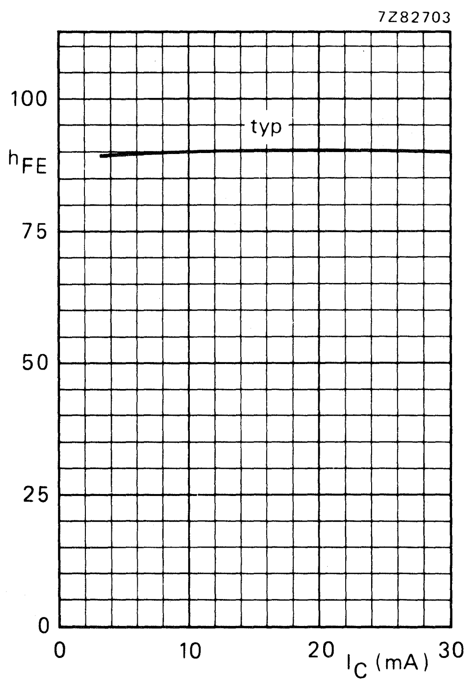


Fig. 4 V_{CE} = 5 V; T_j = 25 °C.

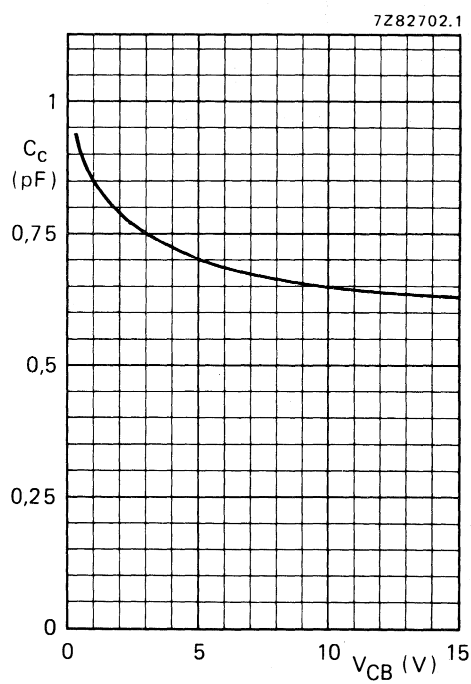


Fig. 5 Typical values collector capacitance
$I_E = I_e = 0$; f = 1 MHz; T_j = 25 °C.

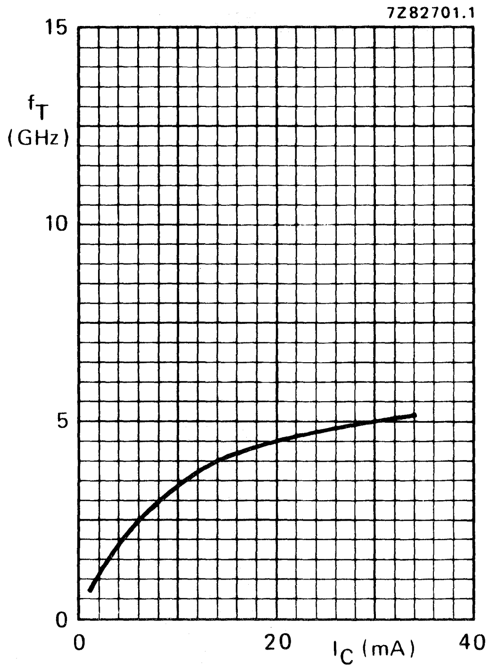


Fig. 6 Typical values transition frequency at V_{CE} = 5 V; f = 500 MHz; T_j = 25 °C.

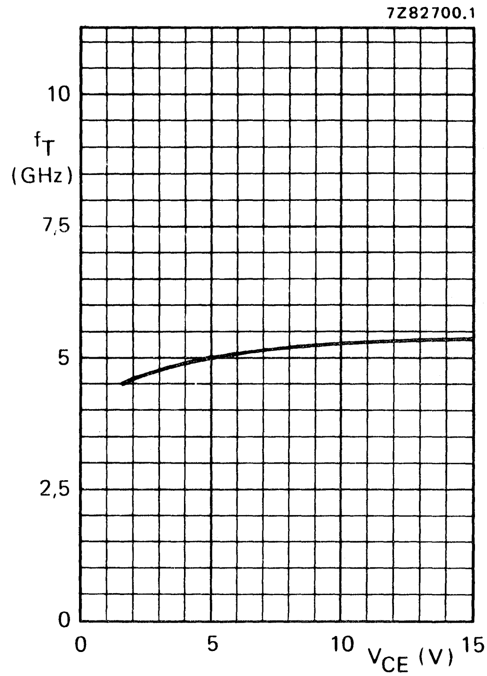


Fig. 7 Typical values transition frequency at I_C = 30 mA; f = 500 MHz; T_j = 25 °C.

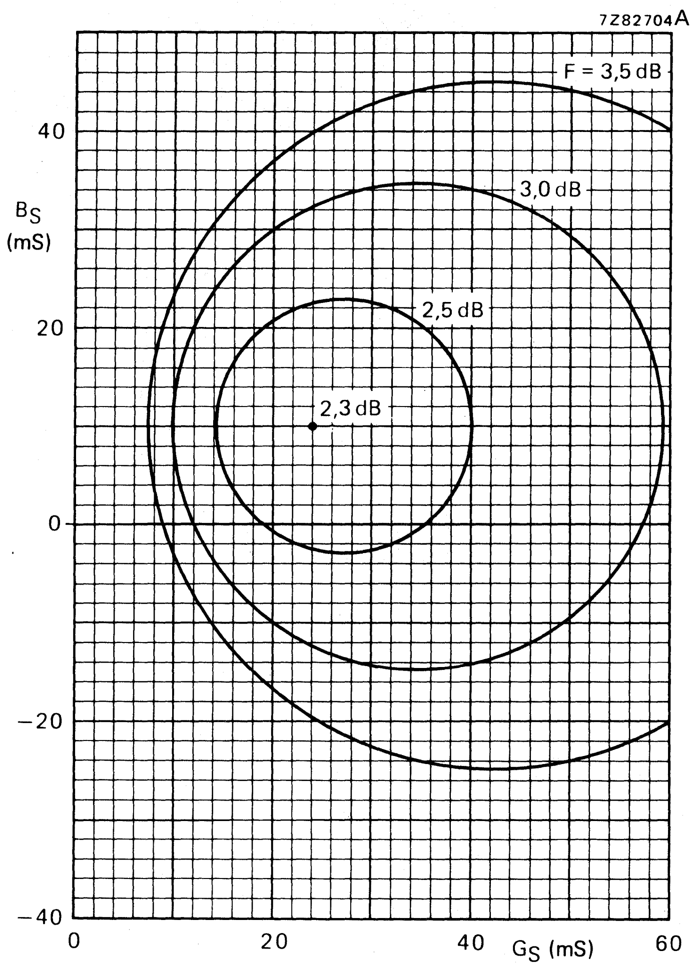


Fig. 8 Circles of constant noise figure.
V_{CE} = 8 V; I_C = 30 mA; f = 800 MHz;
T_{amb} = 25 °C; typical values.

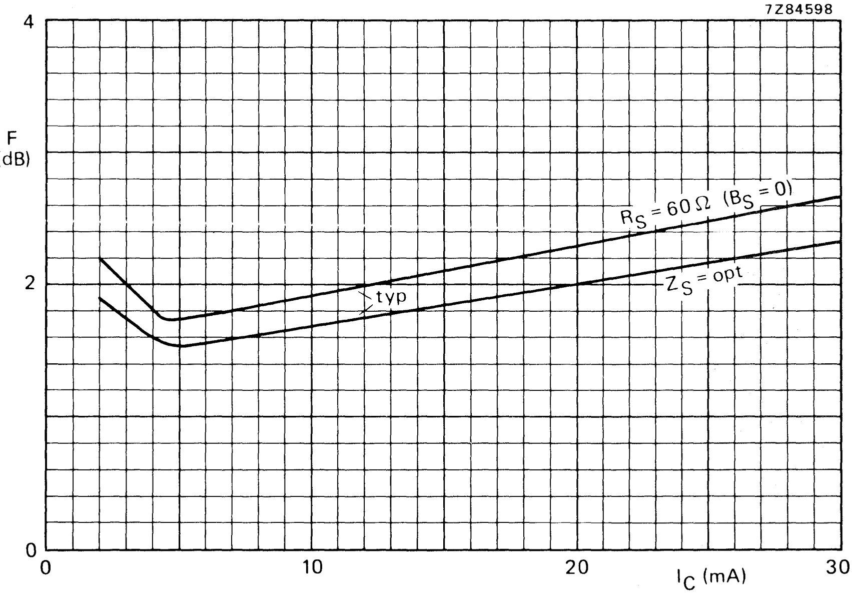


Fig. 9 $V_{CE} = 8$ V; f = 800 MHz; $T_{amb} = 25$ °C.

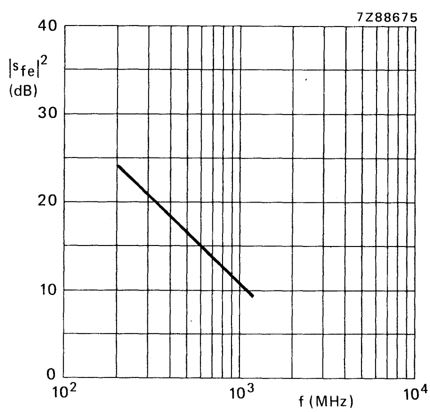


Fig. 10 Typical values forward transmission coefficient as a function of frequency. $V_{CE} = 8$ V; $I_C = 30$ mA; $T_{amb} = 25$ °C.

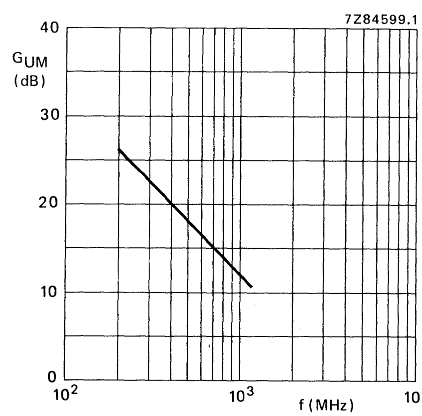


Fig. 11 Typical values unilateral power power gain as a function of frequency. $V_{CE} = 8$ V; $I_C = 30$ mA; $T_{amb} = 25$ °C.

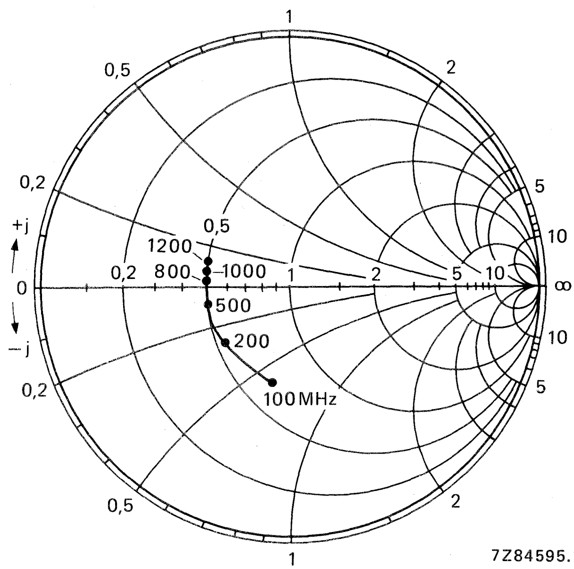


Fig. 12 Input impedance derived from input reflection coefficient s_{ie} co-ordinates in ohm x 50.
V_{CE} = 8 V; I_C = 30 mA; T_{amb} = 25 °C.

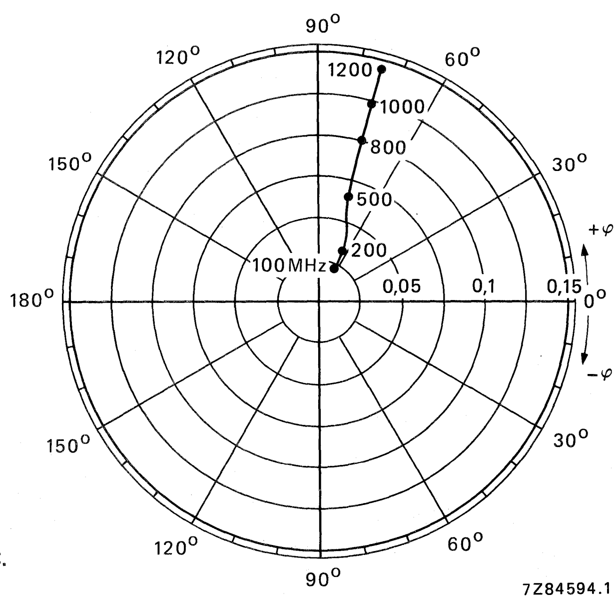


Fig. 13 Reverse transmission coefficient s_{re}.
V_{CE} = 8 V; I_C = 30 mA; T_{amb} = 25 °C.

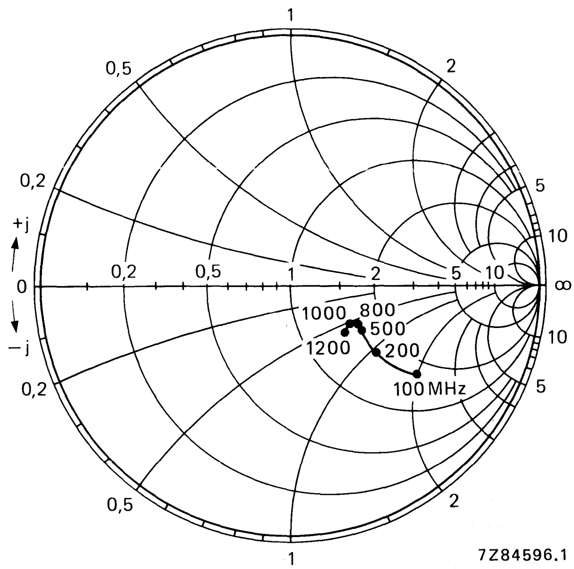


Fig. 14 Output impedance derived from output reflection coefficient s_{oe} co-ordinates in ohm x 50.
V_{CE} = 8 V; I_C = 30 mA; T_{amb} = 25 °C.

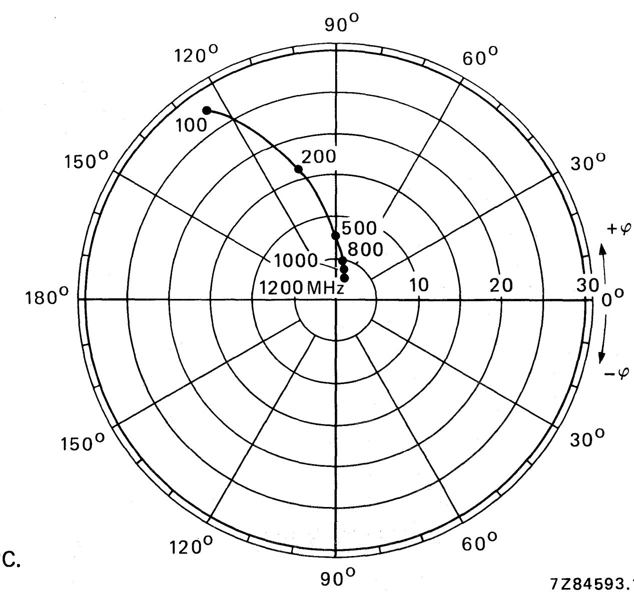


Fig. 15 Forward transmission coefficient s_{fe}.
V_{CE} = 8 V; I_C = 30 mA; T_{amb} = 25 °C.

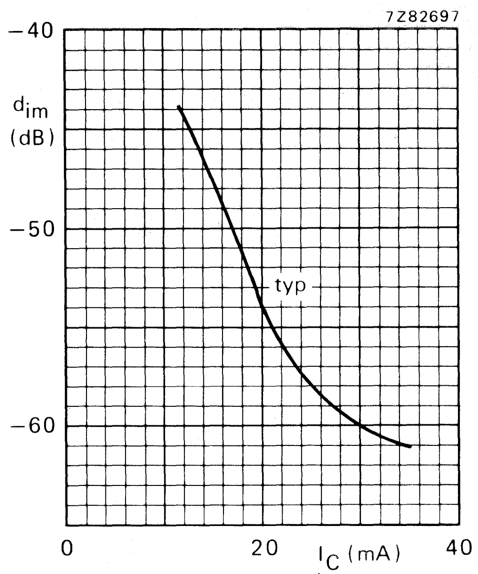


Fig. 16 V_{CE} = 8 V; V_o = 425 mV = 52,6 dBmV; $f_{(p+q-r)}$ = 793,25 MHz; T_{amb} = 25 °C; measured in MATV test circuit (see Fig. 2).

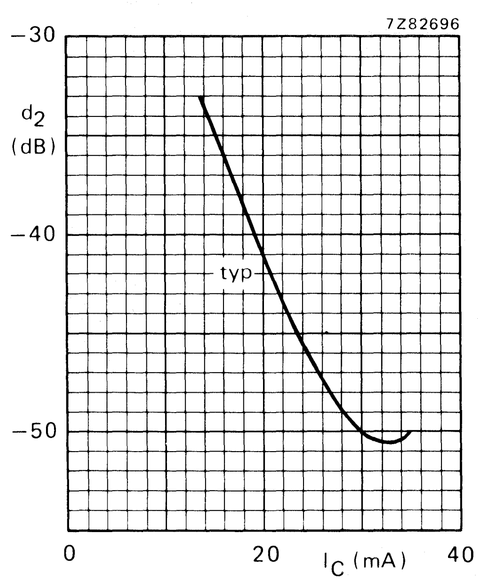


Fig. 17 V_{CE} = 8 V; V_o = 200 mV = 46 dBmV; $f_{(p+q)}$ = 810 MHz; T_{amb} = 25 °C; measured in MATV test circuit (see Fig. 2).

N-CHANNEL JUNCTION FIELD-EFFECT TRANSISTOR

Symmetrical n-channel silicon junction field-effect transistor, designed primarily for use as a source follower with the input protected against successive voltage surges by a forward and reverse integrated diode.

QUICK REFERENCE DATA

Drain-source voltage	$\pm V_{DS}$	max.	30	V
Gate-source voltage (open drain)	$-V_{GS}$	max.	30	V
Total power dissipation up to T_{amb} = 60 °C	P_{tot}	max.	200	mW
Drain current				
V_{DS} = 6 V; V_{GS} = 0: BFR101A	I_{DSS}		0,2 to 1,5	mA
V_{DS} = 6 V; V_{GS} = 0: BFR101B	I_{DSS}		1,0 to 5,0	mA
Transfer admittance (common source)				
V_{DS} = 6 V; V_{GS} = 0; f = 1 kHz: BFR101A	$\lvert y_{fs} \rvert$	>	1,2	mS
V_{DS} = 6 V; V_{GS} = 0; f = 1 kHz: BFR101B	$\lvert y_{fs} \rvert$	>	2,5	mS

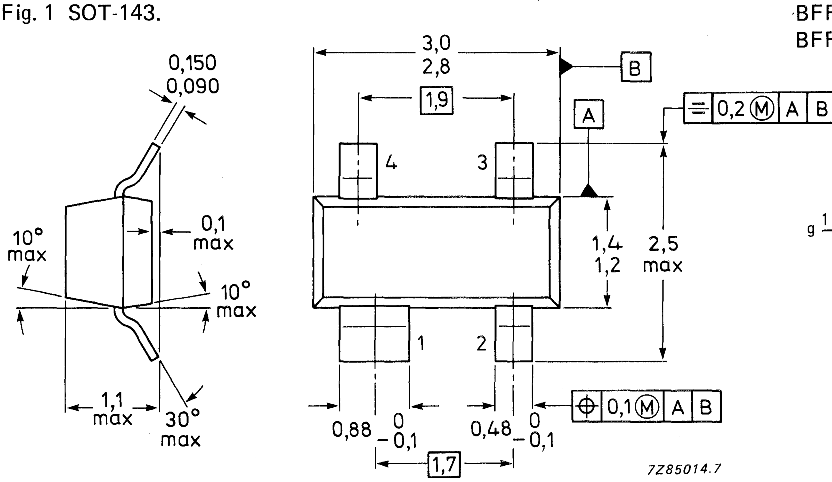
MECHANICAL DATA

Dimensions in mm

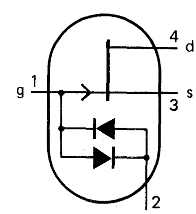
Fig. 1 SOT-143.

Marking code

BFR101A = M97
BFR101B = M98



TOP VIEW



See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	$\pm V_{DS}$	max.	30	V
Drain-gate voltage (open source)	V_{DGO}	max.	30	V
Gate-source voltage (open drain)	$-V_{GSO}$	max.	30	V
Drain current (d.c.)	I_D	max.	20	mA
Gate current (d.c.)	I_G	max.	10	mA
Total power dissipation up to T_{amb} = 60 °C*	P_{tot}	max.	200	mW
Storage temperature	T_{stg}		−65 to + 150	°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE

From junction to ambient in free air*	$R_{th\ j\text{-}a}$	=	460	K/W

CHARACTERISTICS with source connected to case for all measurements

T_{amb} = 25 °C unless otherwise specified

		BFR101A	BFR101B	
Gate leakage current V_{DS} = 6 V; I_D = 10 μA	$-I_G$	< 5	5	nA
Drain current* V_{DS} = 6 V; V_{GS} = 0	I_{DSS}	0,2 to 1,5	1 to 5	mA
Gate-source cut-off voltage V_{DS} = 6 V; I_D = 1 μA	$-V_{(P)GS}$	0,2 to 1	0,5 to 2,5	V
Small-signal common-source characteristics V_{DS} = 6 V; V_{GS} = 0				
Transfer admittance* f = 1 kHz	$\|y_{fs}\|$	> 1,2	2,5	mS
Output admittance at f = 1 kHz**	$\|y_{os}\|$	typ. 10	50	mS
Input capacitance at f = 1 MHz diodes not connected	C_{is}	< 5	5	pF
Diode capacitance V_D = 0; source and drain not connected	C_d	typ. 0,7	0,7	pF
Diode forward voltage $\pm I_F$ = 10 mA	V_F	0,7 to 1,2	0,7 to 1,2	V

→ * Device mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.
** Measured under pulse conditions: t_p = 100 ms; $\delta \leqslant 0{,}1$.

N-P-N H.F. WIDEBAND TRANSISTOR

N-P-N transistor in a plastic SOT-23 envelope. It is intended for a wide range of v.h.f. and u.h.f. applications in thick and thin-film circuits.

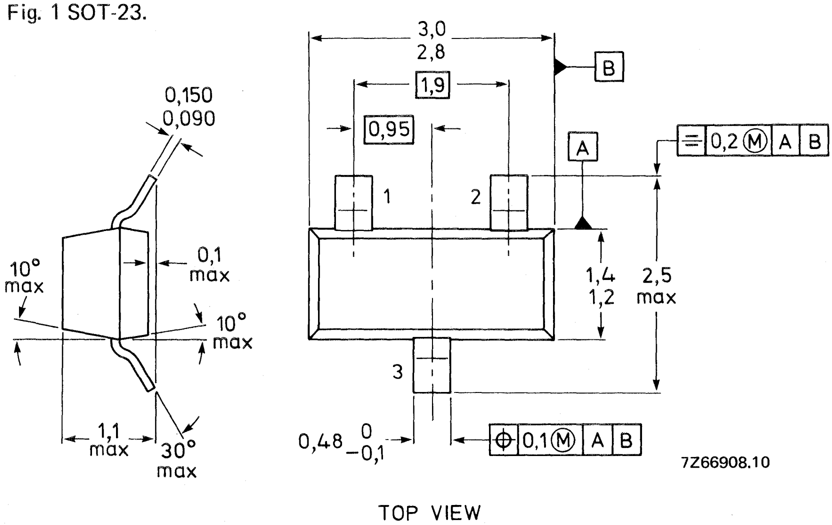
QUICK REFERENCE DATA

Collector-base voltage (open emitter; peak value)	V_{CBOM}	max.	25	V
Collector-emitter voltage (open base)	V_{CEO}	max.	15	V
Collector current (peak value)	I_{CM}	max.	50	mA
Total power dissipation up to T_{amb} = 65 °C	P_{tot}	max.	250	mW
Junction temperature	T_j	max.	175	°C
D.C. current gain I_C = 2 mA; V_{CE} = 1 V	h_{FE}		20 to 150	
Transition frequency I_C = 25 mA; V_{CE} = 5 V; f = 500 MHz	f_T	typ.	1,3	GHz
Noise figure I_C = 2 mA; V_{CE} = 5 V; R_S = 50 Ω; f = 500 MHz	F	typ.	4,5	dB

MECHANICAL DATA

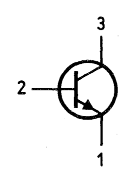
Dimensions in mm

Fig. 1 SOT-23.



Marking code

BFS17 = E1



If required, the R-version (reverse pinning) is available on request.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter; peak value)	V_{CBOM}	max.	25 V
Collector-emitter voltage (open base) I_C = 10 mA	V_{CEO}	max.	15 V
Emitter-base voltage (open collector)	V_{EBO}	max.	2,5 V
Collector current (d.c.)	I_C	max.	25 mA
Collector current (peak value)	I_{CM}	max.	50 mA
Total power dissipation up to T_{amb} = 65 °C**	P_{tot}	max.	250 mW
Storage temperature	T_{stg}	−65 to + 175 °C	
Junction temperature	T_j	max.	175 °C

THERMAL CHARACTERISTICS*

$T_j = P\,(R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	60 K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280 K/W
From soldering points to ambient**	$R_{th\ s\text{-}a}$	=	90 K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current			
I_E = 0; V_{CB} = 10 V	I_{CBO}	max.	10 nA
I_E = 0; V_{CB} = 10 V; T_j = 100 °C	I_{CBO}	max.	10 μA
D.C. current gain			
I_C = 2 mA; V_{CE} = 1 V	h_{FE}	20 to 150	
I_C = 25 mA; V_{CE} = 1 V	h_{FE}	min.	20
Transition frequency			
I_C = 2 mA; V_{CE} = 5 V; f = 500 MHz	f_T	typ.	1,0 GHz
I_C = 25 mA; V_{CE} = 5 V; f = 500 MHz	f_T	typ.	1,3 GHz
Collector capacitance at f = 1 MHz			
$I_E = I_e$ = 0; V_{CB} = 10 V	C_c	max.	1,5 pF

* See *Thermal characteristics.*
** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

Emitter capacitance at f = 1 MHz			
$I_C = I_c = 0$; $V_{EB} = 0,5$ V	C_e	max.	2,0 pF
Feedback capacitance at f = 1 MHz			
$I_C = 1$ mA; $V_{CE} = 5$ V	C_{re}	typ.	0,65 pF
Noise figure*			
$I_C = 2$ mA; $V_{CE} = 5$ V;			
f = 500 MHz; $R_S = 50\ \Omega$	F	typ.	4,5 dB
Intermodulation distortion			
$I_C = 10$ mA; $V_{CE} = 6$ V; $R_L = 37,5\ \Omega$; $T_{amb} = 25\ ^oC$			
$V_o = 100$ mV at $f_p = 183$ MHz			
$V_o = 100$ mV at $f_q = 200$ MHz			
measured at $f_{(2q-p)} = 217$ MHz	d_{im}	typ.	−45 dB

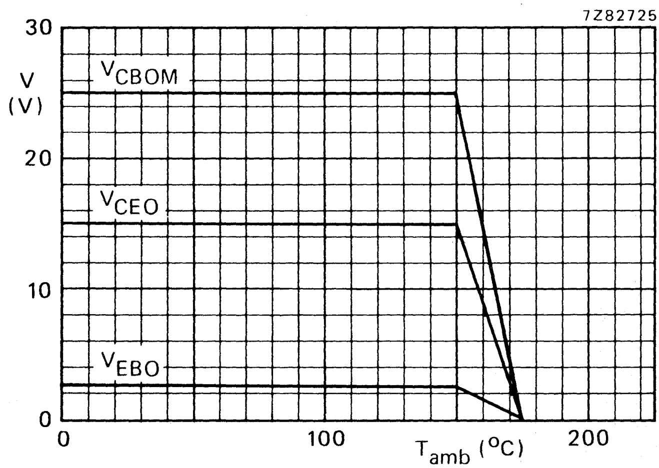


Fig. 2 Voltage derating curve.

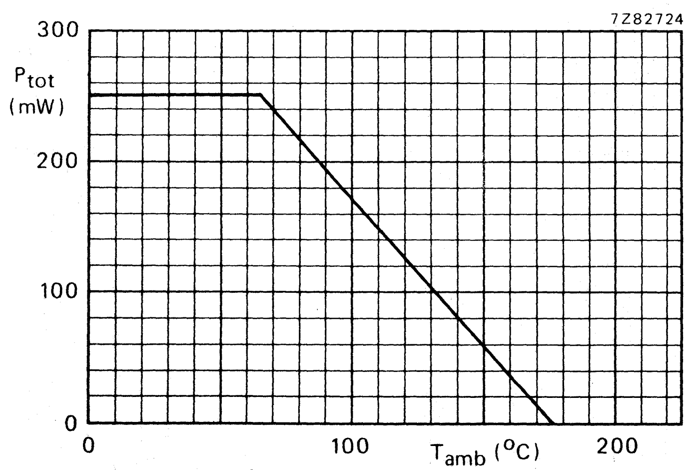


Fig. 3 Power derating curve.

* Crystal mounted in a BFY90 envelope.

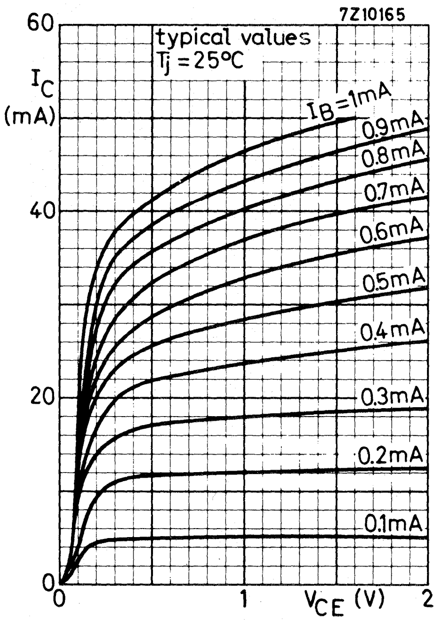


Fig. 4 T_j = 25 °C; typical values.

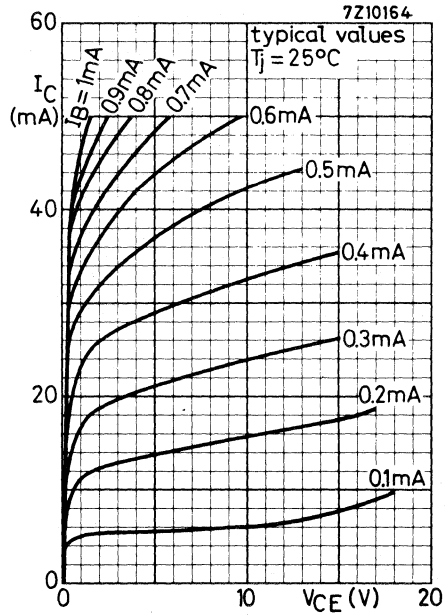


Fig. 5 T_j = 25 °C; typical values.

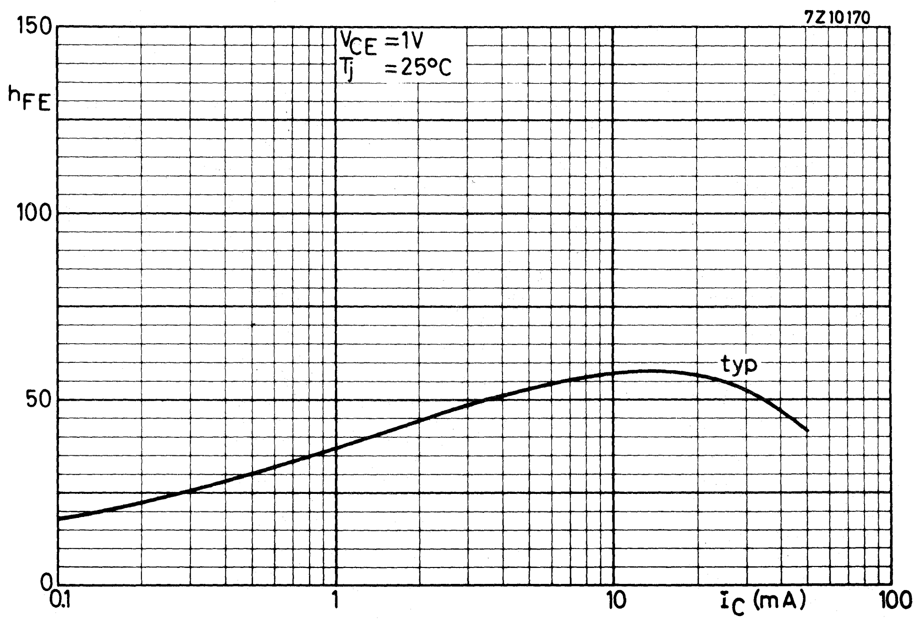


Fig. 6 V_{CE} = 1 V; T_j = 25 °C; typical values.

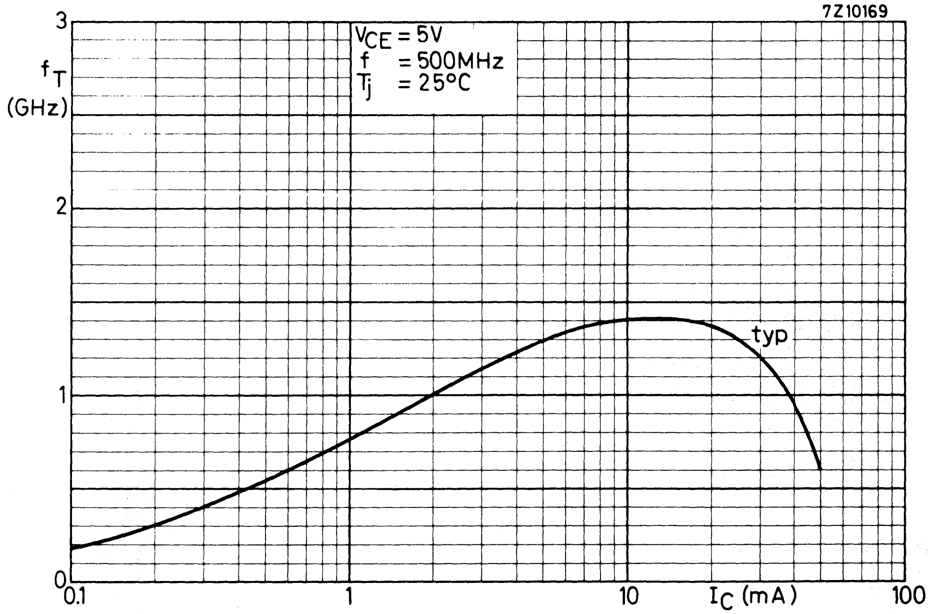


Fig. 7 V_{CE} = 5 V; f = 500 MHz; T_j = 25 °C; typical values.

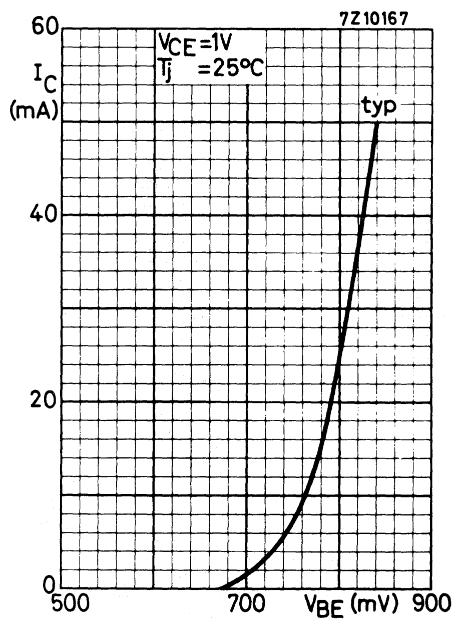


Fig. 8 V_{CE} = 1 V; T_j = 25 °C; typical values.

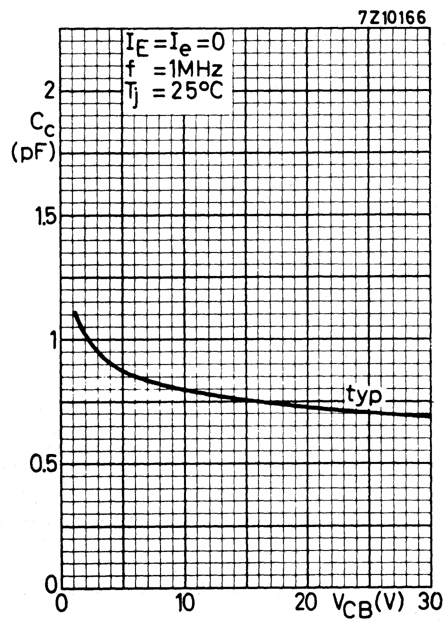


Fig. 9 I_E = I_e = 0; f = 1 MHz; T_j = 25 °C; typical values.

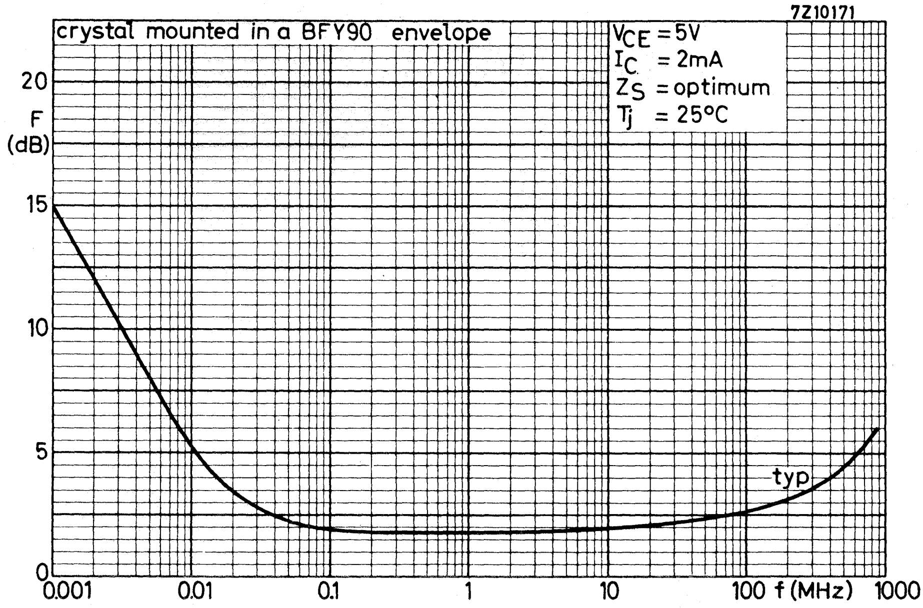


Fig. 10 V_{CE} = 5 V; I_C = 2 mA; Z_S = optimum; T_j = 25 °C; typical values.

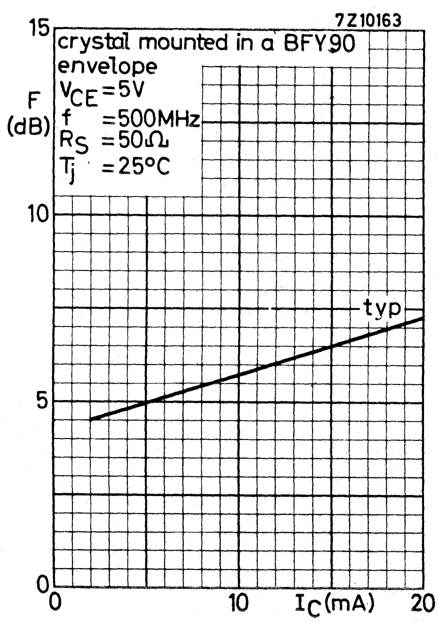


Fig. 11 V_{CE} = 5 V; f = 500 MHz; R_S = 50 Ω; T_j = 25 °C; typical values.

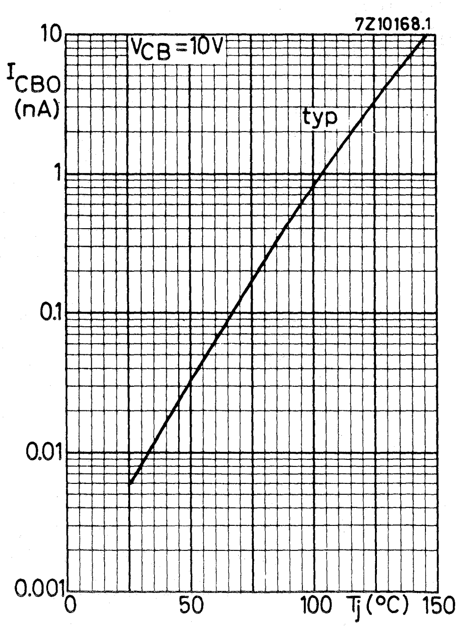


Fig. 12 V_{CB} = 10 V; typical values.

SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N transistors in a microminiature plastic envelope. They are intended for general purpose and h.f. applications in thick and thin-film circuits.

QUICK REFERENCE DATA

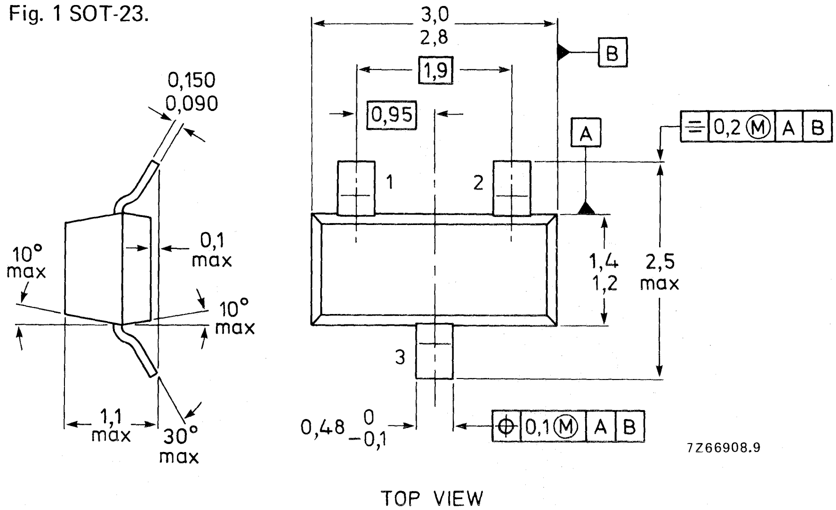
Collector-base voltage (open emitter)	V_{CBO}	max.	30	V
Collector-emitter voltage (open base)	V_{CEO}	max.	20	V
Collector current (d.c.)	I_C	max.	30	mA
Total power dissipation up to T_{amb} = 40 °C	P_{tot}	max.	250	mW
Junction temperature	T_j	max.	150	°C

			BFS18	BFS19	
D.C. current gain I_C = 1 mA; V_{CE} = 10 V	h_{FE}		35 to 125	65 to 225	
Transition frequency at f = 100 MHz I_C = 1 mA; V_{CE} = 10 V	f_T	typ.	200	260	MHz
Noise figure at f = 100 MHz I_C = 1 mA; V_{CE} = 10 V; G_S = 10 mS	F	typ.	4		dB

MECHANICAL DATA

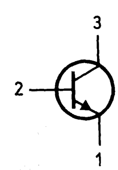
Dimensions in mm

Fig. 1 SOT-23.

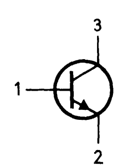


Marking code

BFS18 = F1
BFS19 = F2



BFS18R = F4
BFS19R = F5



R-types are available on request.
See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter) See Fig. 2	V_{CBO}	max.	30	V
Collector-emitter voltage (open base) See Fig. 2 $I_C = 2$ mA	V_{CEO}	max.	20	V
Emitter-base voltage (open collector) See Fig. 2	V_{EBO}	max.	5	V
Collector current (d.c.)	I_C	max.	30	mA
Collector current (peak value)	I_{CM}	max.	30	mA
Total power dissipation up to $T_{amb} = 40$ °C**	P_{tot}	max.	250	mW
Storage temperature	T_{stg}		−65 to + 150	°C
Junction temperature	T_j	max.	150	°C

THERMAL CHARACTERISTICS*

$T_j = P\,(R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	60	K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280	K/W
From soldering points to ambient**	$R_{th\ s\text{-}a}$	=	90	K/W

CHARACTERISTICS

$T_j = 25$ °C unless otherwise specified

Collector cut-off current $I_E = 0$; $V_{CB} = 20$ V	I_{CBO}	<	100		nA
$I_E = 0$; $V_{CB} = 20$ V; $T_j = 100$ °C	I_{CBO}	<	10		µA
Base-emitter voltage $I_C = 1$ mA; $V_{CE} = 10$ V	V_{BE}		0,65 to 0,74		V
			BFS18	BFS19	
D.C. current gain $I_C = 1$ mA; $V_{CE} = 10$ V	h_{FE}		35 to 125	65 to 225	
Transition frequency at f = 100 MHz $I_C = 1$ mA; $V_{CE} = 10$ V	f_T	typ.	200	260	MHz
Collector capacitance at f = 1 MHz $I_E = I_e = 0$; $V_{CB} = 10$ V	C_c	typ.	1		pF
Feedback capacitance at f = 1 MHz $I_C = 1$ mA; $V_{CE} = 10$ V	$-C_{re}$	typ.	0,85		pF
Noise figure▲ $I_C = 1$ mA; $V_{CE} = 10$ V; $G_S = 10$ mS ; f = 100 MHz	F	typ.	4		dB

* See *Thermal characteristics.*
** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.
▲ Crystal mounted in a BF115 enve

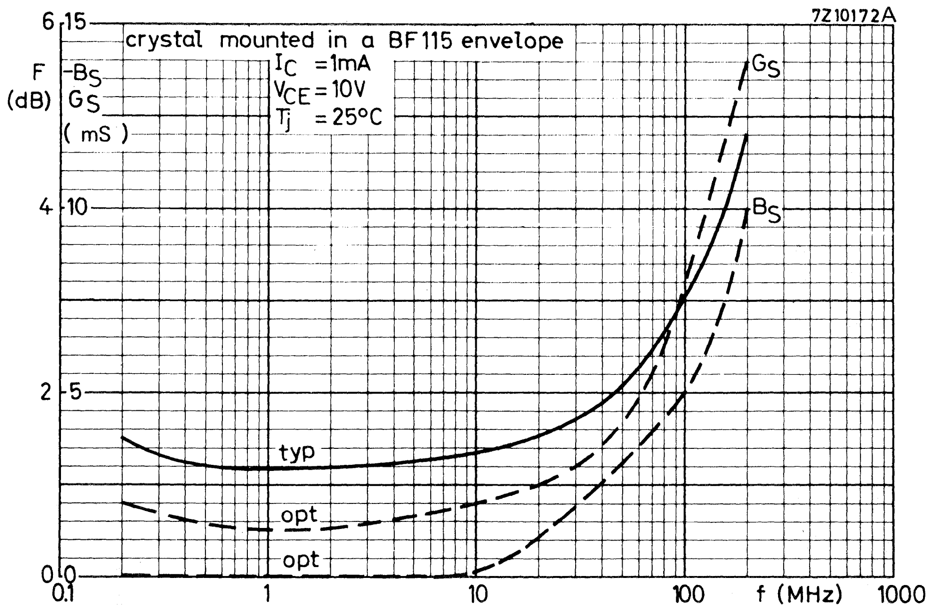


Fig. 2.

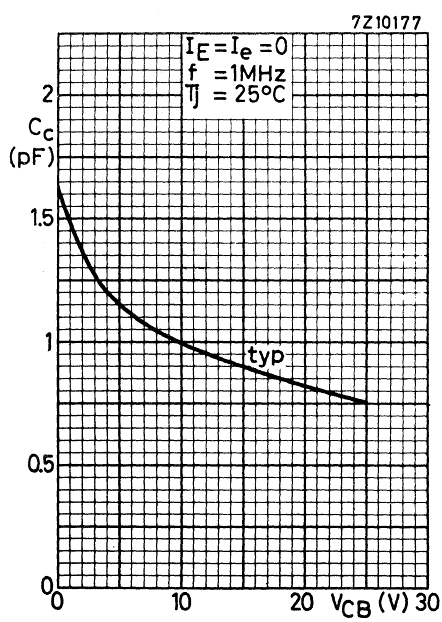


Fig. 3.

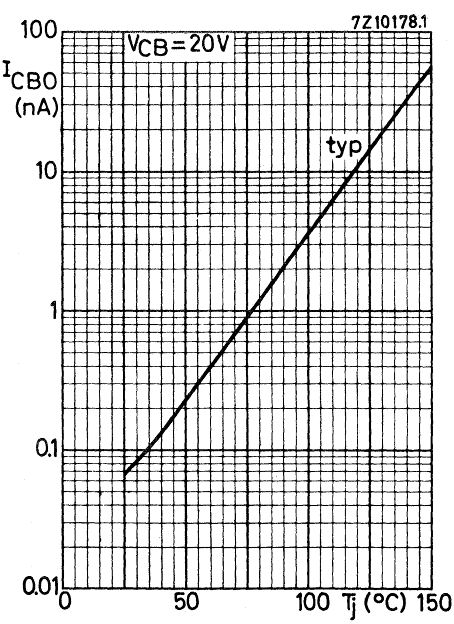


Fig. 4.

Typical behaviour of collector current versus collector-emitter voltage

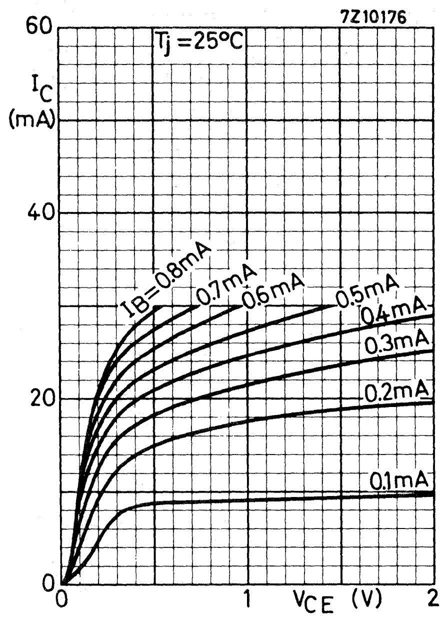


Fig. 5.

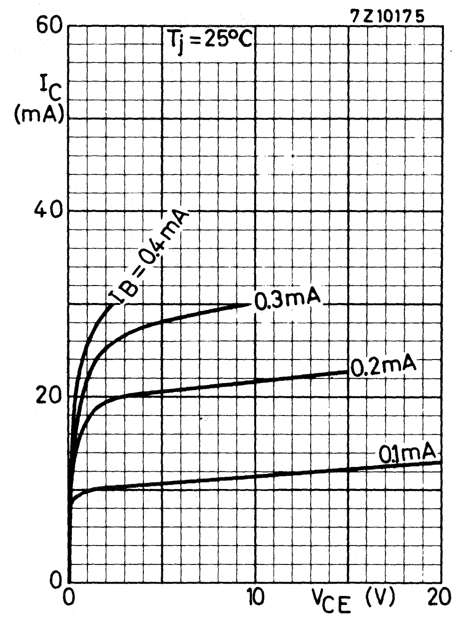


Fig. 6.

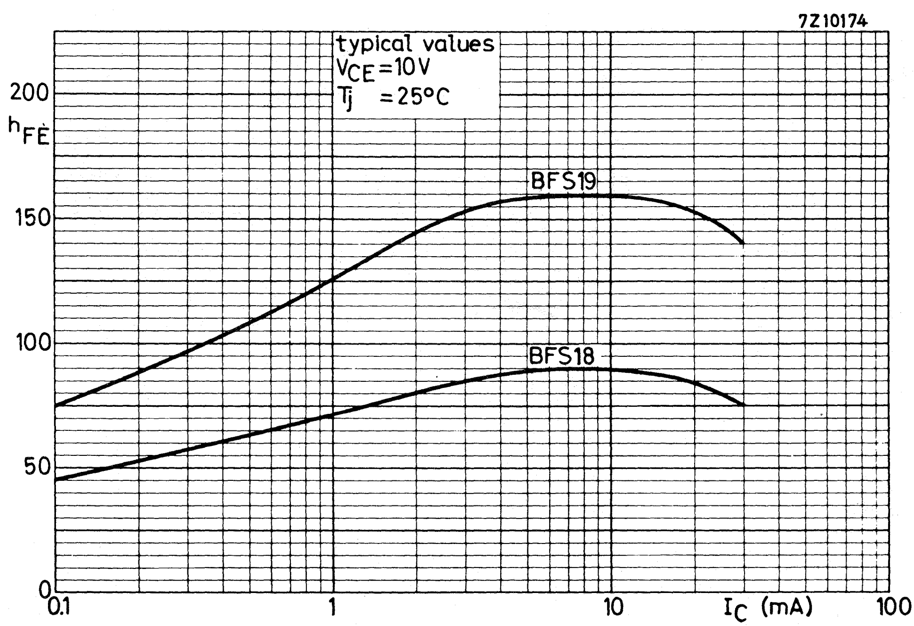


Fig. 7.

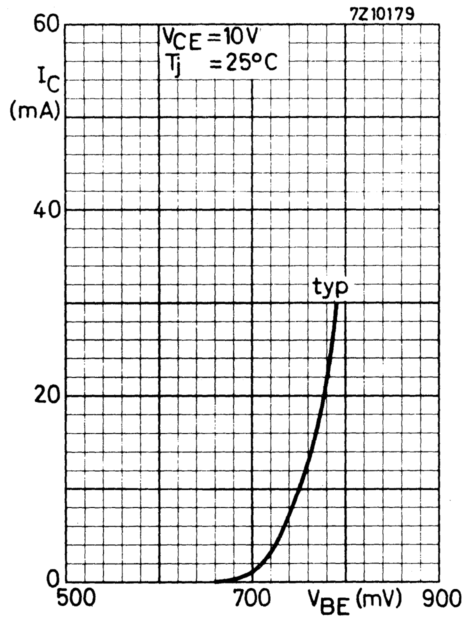

7Z10179
60
I_C
(mA)
40
20
0
500
700
V_{BE} (mV)
900
V_{CE} = 10 V
T_j = 25°C
typ

Fig. 8.

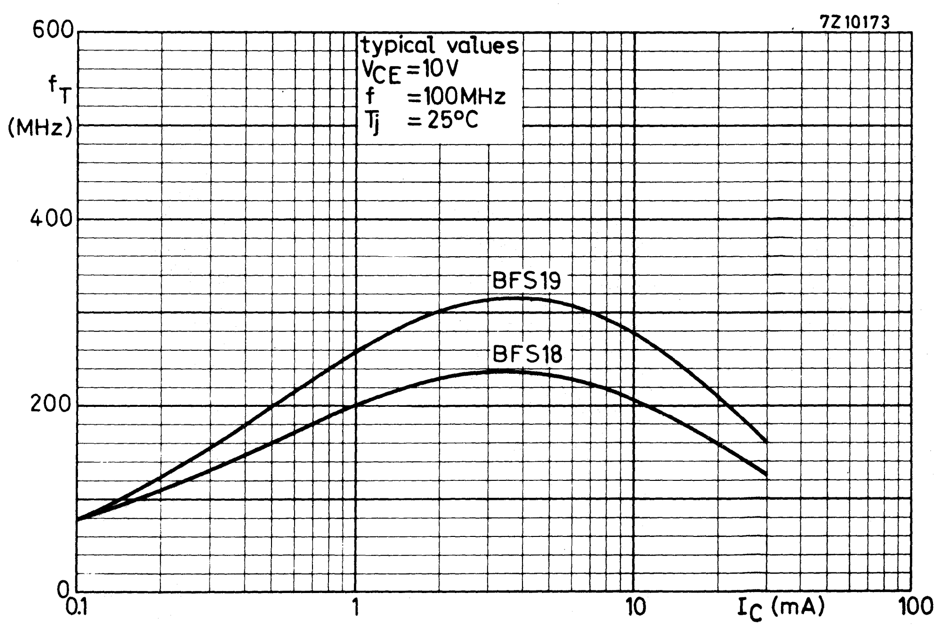

7Z10173
600
f_T
(MHz)
400
200
0
0.1
1
10
I_C (mA)
100
typical values
V_{CE} = 10 V
f = 100 MHz
T_j = 25°C
BFS19
BFS18

Fig. 9.

SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N transistor in a microminiature plastic envelope. It has a very low feedback capacitance and is intended for i.f. and v.h.f. applications in thick and thin-film circuits.

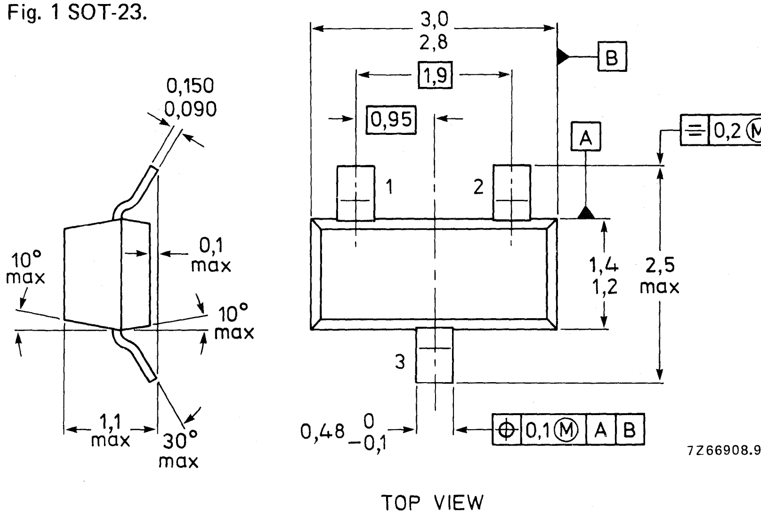
QUICK REFERENCE DATA

Collector-base voltage (open emitter)	V_{CBO}	max.	30	V
Collector-emitter voltage (open base)	V_{CEO}	max.	20	V
Collector current (d.c.)	I_C	max.	25	mA
Total power dissipation up to T_{amb} = 40 °C	P_{tot}	max.	250	mW
Junction temperature	T_j	max.	150	°C
D.C. current gain I_C = 7 mA; V_{CE} = 10 V	h_{FE}	>	40	
Transition frequency at f = 100 MHz I_C = 5 mA; V_{CE} = 5 V	f_T	typ.	450	MHz
Feedback capacitance at f = 1 MHz I_C = 1 mA; V_{CE} = 10 V	C_{re}	typ.	350	fF

MECHANICAL DATA

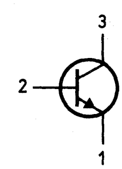
Dimensions in mm

Fig. 1 SOT-23.

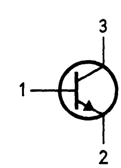


Marking code

BFS20 = G1



BFS20R = G4



R-types are available on request

See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter) see Fig. 2	V_{CBO}	max.	30	V
Collector-emitter voltage (open base) see Fig. 2 $I_C = 2$ mA	V_{CEO}	max.	20	V
Emitter-base voltage (open collector) see Fig. 2	V_{EBO}	max.	4	V
Collector current (d.c.)	I_C	max.	25	mA
Collector current (peak value)	I_{CM}	max.	25	mA
Total power dissipation up to $T_{amb} = 40\ ^oC$**	P_{tot}	max.	250	mW
Storage temperature	T_{stg}	−65 to	+150	^oC
Junction temperature	T_j	max.	150	^oC

THERMAL CHARACTERISTICS *

$T_j = P \times (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	60	K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280	K/W
From soldering points to ambient **	$R_{th\ s\text{-}a}$	=	90	K/W

CHARACTERISTICS

$T_j = 25\ ^oC$ unless otherwise specified

Collector cut-off current				
$I_E = 0$; $V_{CB} = 20$ V	I_{CBO}	<	100	nA
$I_E = 0$; $V_{CB} = 20$ V; $T_j = 100\ ^oC$	I_{CBO}	<	10	μA
Base-emitter voltage				
$I_C = 7$ mA; $V_{CE} = 10$ V	V_{BE}	typ.	740	mV
		<	900	mV
D.C. current gain				
$I_C = 7$ mA; $V_{CE} = 10$ V	h_{FE}	>	40	
		typ.	85	
Transition frequency at f = 100 MHz				
$I_C = 5$ mA; $V_{CE} = 10$ V	f_T	>	275	MHz
		typ.	450	MHz
Collector capacitance at f = 1 MHz				
$I_E = I_e = 0$; $V_{CB} = 10$ V	C_c	typ.	0,8	pF
Feedback capacitance at f = 1 MHz				
$I_C = 1$ mA; $V_{CE} = 10$ V	$-C_{re}$	typ.	350	fF

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

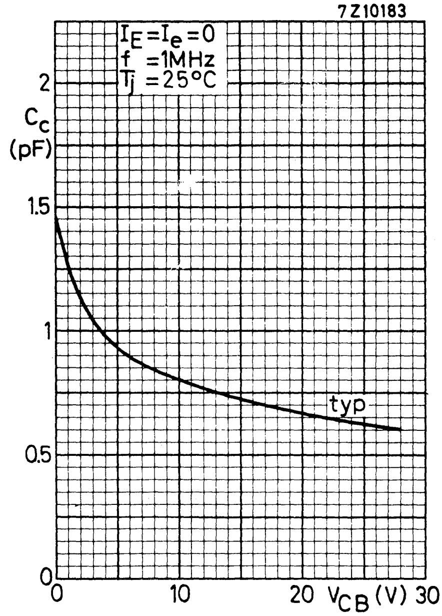

7Z10183
$I_E = I_e = 0$
f = 1MHz
$T_j = 25°C$
2
C_c
(pF)
1.5
1
0.5
0
typ
0
10
20
V_{CB} (V)
30

Fig. 2.

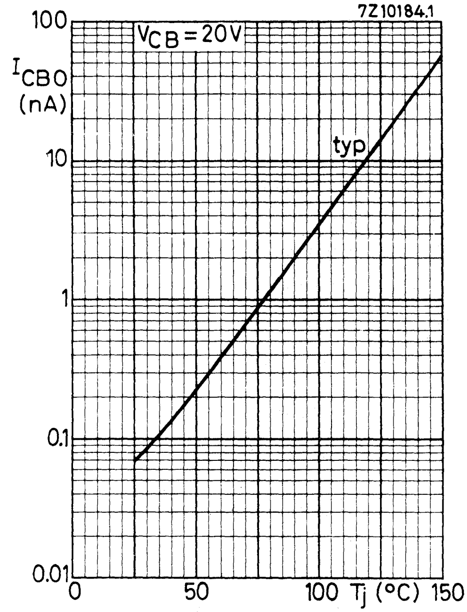

7Z10184.1
100
$V_{CB} = 20V$
I_{CBO}
(nA)
10
typ
1
0.1
0.01
0
50
100
T_j (°C)
150

Fig. 3.

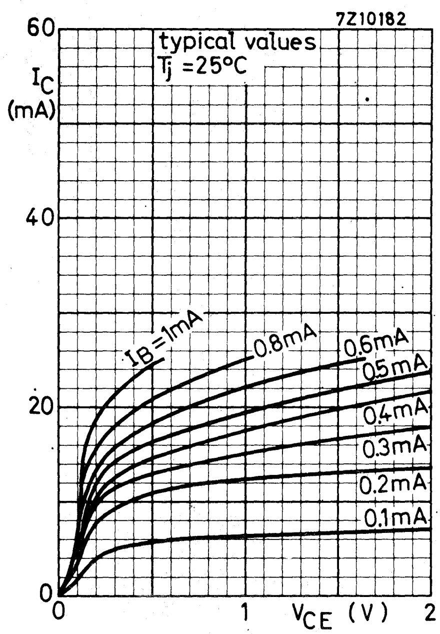


Fig. 4.

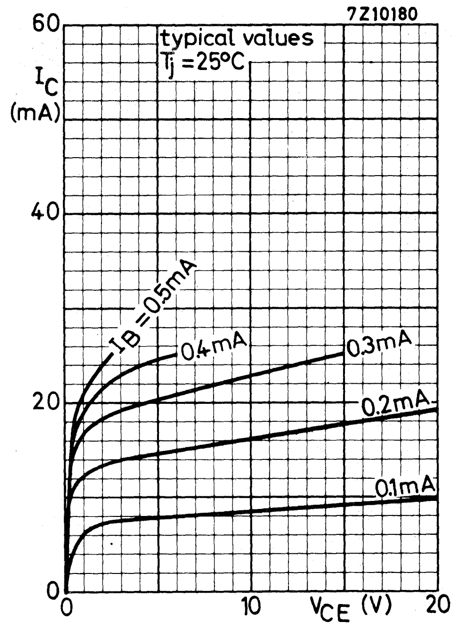


Fig. 5.

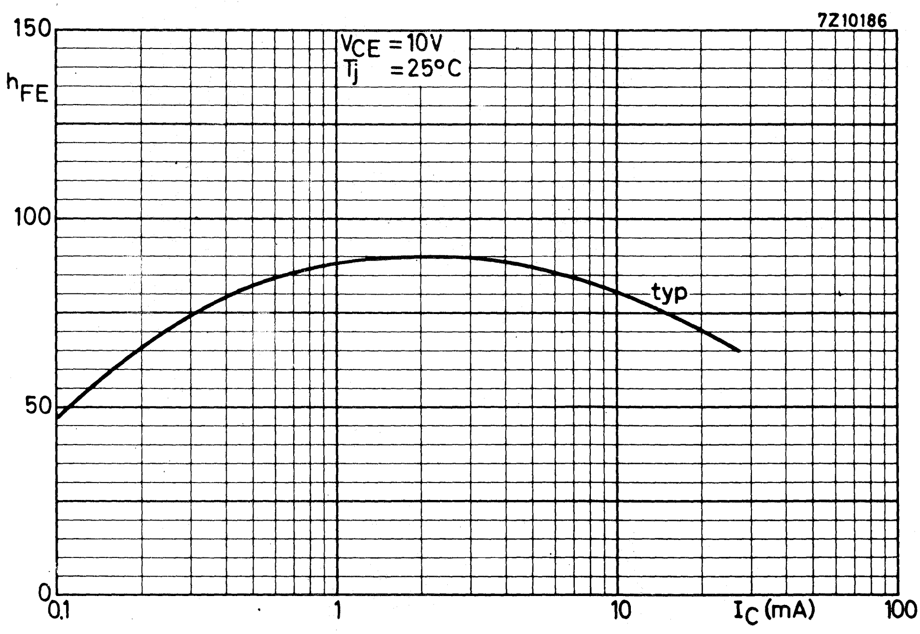


Fig. 6.

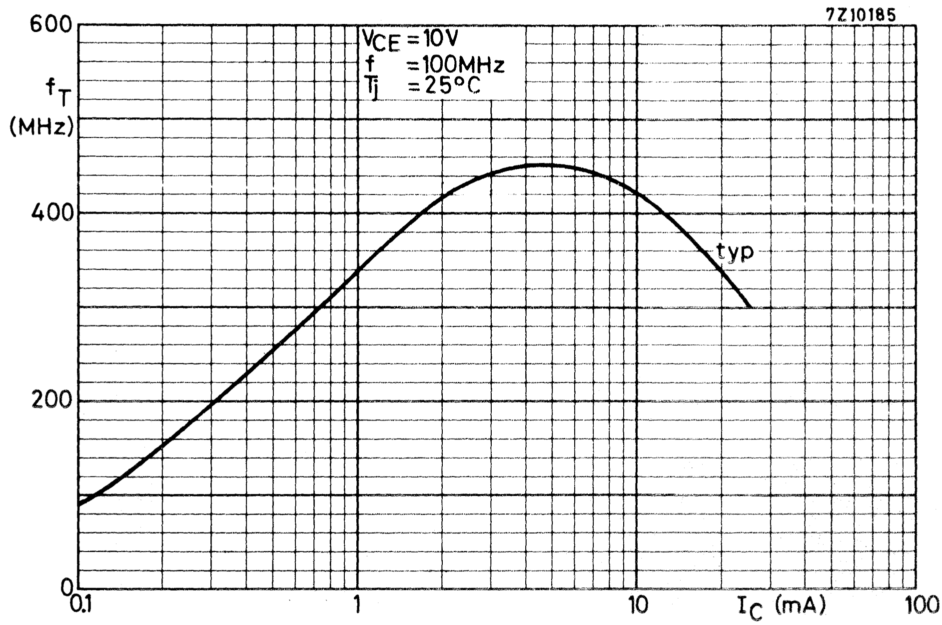

7Z10185
V_{CE} = 10 V
f = 100 MHz
T_j = 25 °C
f_T
(MHz)
600
400
200
0
typ
0.1
1
10
I_C (mA)
100

Fig. 7.

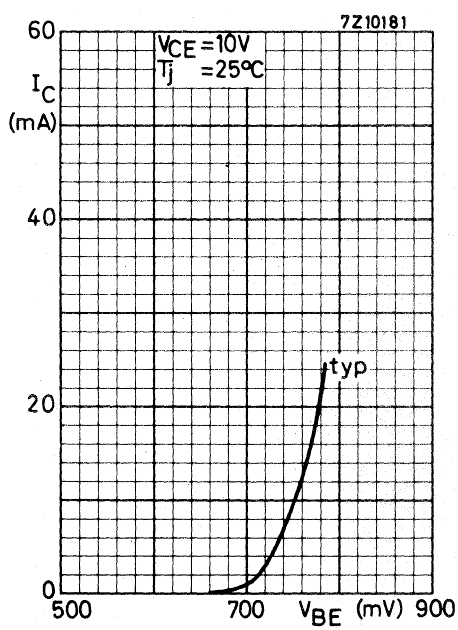

7Z10181
V_{CE} = 10 V
T_j = 25 °C
I_C
(mA)
60
40
20
0
typ
500
700
V_{BE} (mV)
900

Fig. 8.

N-P-N H.F. WIDEBAND TRANSISTOR

N-P-N transistor in a plastic SOT-23 envelope, primarily intended for use in u.h.f. low power amplifiers in thick and thin-film circuits, such as in pocket phones, paging systems, etc. The transistor features low current consumption (100 μA – 1 mA); thanks to its high transition frequency, it also has excellent wideband properties and low noise up to high frequencies.

QUICK REFERENCE DATA

Collector-base voltage (open emitter)	V_{CBO}	max.	8	V
Collector-emitter voltage (open base)	V_{CEO}	max.	5	V
Collector current (d.c.)	I_C	max.	6,5	mA
Total power dissipation up to T_{amb} = 125 °C	P_{tot}	max.	50	mW
Junction temperature	T_j	max.	150	°C
Transition frequency at f = 500 MHz I_C = 1 mA; V_{CE} = 1 V	f_T	typ.	2,3	GHz
Feedback capacitance at f = 1 MHz I_C = 1 mA; V_{CE} = 1 V	C_{re}	max.	0,45	pF
Noise figure at optimum source impedance I_C = 1 mA; V_{CE} = 1 V; f = 500 MHz	F	typ.	3,8	dB
Max. unilateral power gain I_C = 1 mA; V_{CE} = 1 V; f = 500 MHz	G_{UM}	typ.	18	dB

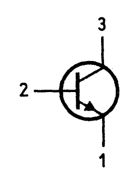
MECHANICAL DATA

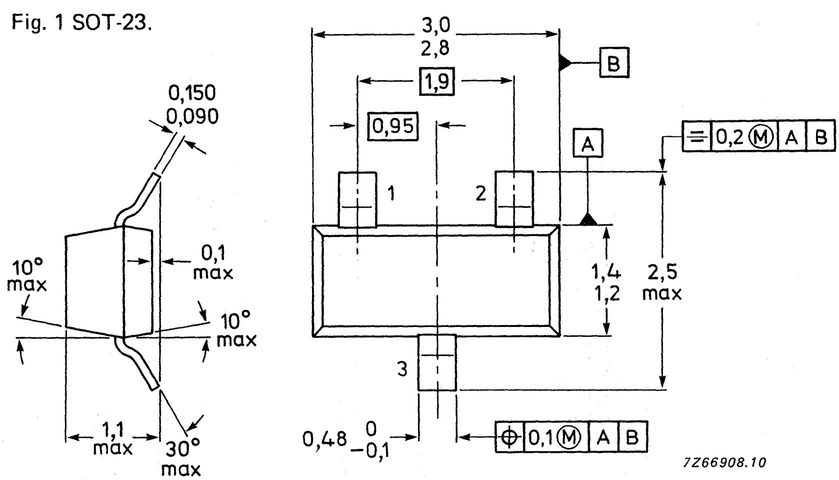
Dimensions in mm

Fig. 1 SOT-23.

Marking code

BFT25 = V1





TOP VIEW

If required, the R-version (reverse pinning) is available on request.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	V_{CBO}	max.	8	V
Collector-emitter voltage (open base)	V_{CEO}	max.	5	V
Emitter-base voltage (open collector)	V_{EBO}	max.	2	V
Collector current (d.c.)	I_C	max.	6,5	mA
Collector current (peak value; f > 1 MHz)	I_{CM}	max.	10	mA
Total power dissipation up to T_{amb} = 125 °C**	P_{tot}	max.	50	mW
Storage temperature	T_{stg}	−65 to + 150		°C
Junction temperature	T_j	max.	150	°C

THERMAL CHARACTERISTICS*

$T_j = P \times (R_{th\,j\text{-}t} + R_{th\,t\text{-}s} + R_{th\,s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\,j\text{-}t}$	=	60	K/W
From tab to soldering points	$R_{th\,t\text{-}s}$	=	280	K/W
From soldering points to ambient**	$R_{th\,s\text{-}a}$	=	90	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current				
$I_E = 0$; $V_{CB} = 5$ V	I_{CBO}	max.	50	nA
D.C. current gain				
$I_C = 10\ \mu A$; $V_{CE} = 1$ V	h_{FE}	min.	20	
		typ.	30	
$I_C = 1$ mA; $V_{CE} = 1$ V	h_{FE}	min.	20	
		typ.	40	
Saturation voltages				
$I_C = 10\ \mu A$; $I_B = 1\ \mu A$	V_{CEsat}	max.	200	mV
	V_{BEsat}	max.	750	mV
$I_C = 1$ mA; $I_B = 0,1$ mA	V_{CEsat}	max.	175	mV
	V_{BEsat}	max.	900	mV
Transition frequency at f = 500 MHz				
$I_C = 1$ mA; $V_{CE} = 1$ V	f_T	min.	1,2	GHz
		typ.	2,3	GHz

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

Collector capacitance at f = 1 MHz			
$I_E = I_e = 0$; $V_{CB} = 0,5$ V	C_c	max.	0,6 pF
Emitter capacitance at f = 1 MHz			
$I_C = I_c = 0$; $V_{EB} = 0$	C_e	max.	0,5 pF
Feedback capacitance at f = 1 MHz			
$I_C = 1$ mA; $V_{CE} = 1$ V; $T_{amb} = 25\ ^oC$	C_{re}	max.	0,45 pF
Noise figure at optimum source impedance			
$I_C = 0,1$ mA; $V_{CE} = 1$ V; f = 500 MHz; $T_{amb} = 25\ ^oC$	F	typ.	5,5 dB
$I_C = 1$ mA; $V_{CE} = 1$ V; f = 500 MHz; $T_{amb} = 25\ ^oC$	F	typ.	3,8 dB

Maximum unilateral power gain (s_{re} assumed to be zero)

$$G_{UM} \text{ (in dB)} = 10 \log \frac{|s_{fe}|^2}{(1 - |s_{ie}|^2)(1 - |s_{oe}|^2)}$$

$I_C = 1$ mA; $V_{CE} = 1$ V; f = 200 MHz; $T_{amb} = 25\ ^oC$	G_{UM}	typ.	25,0 dB
$I_C = 1$ mA; $V_{CE} = 1$ V; f = 500 MHz; $T_{amb} = 25\ ^oC$	G_{UM}	typ.	18,0 dB
$I_C = 1$ mA; $V_{CE} = 1$ V; f = 800 MHz; $T_{amb} = 25\ ^oC$	G_{UM}	typ.	12,0 dB

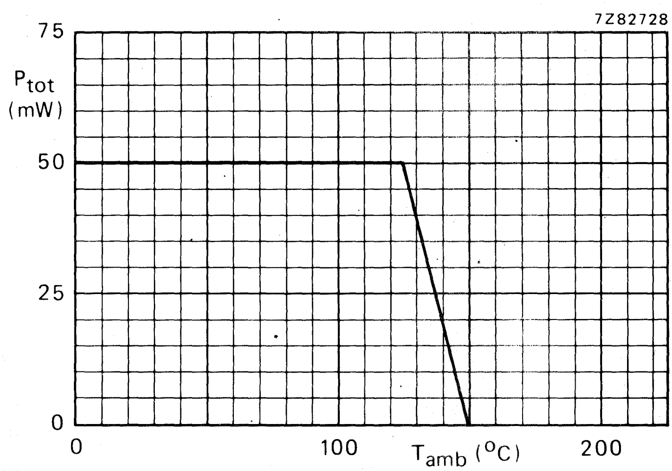


Fig. 2 Power derating curve.

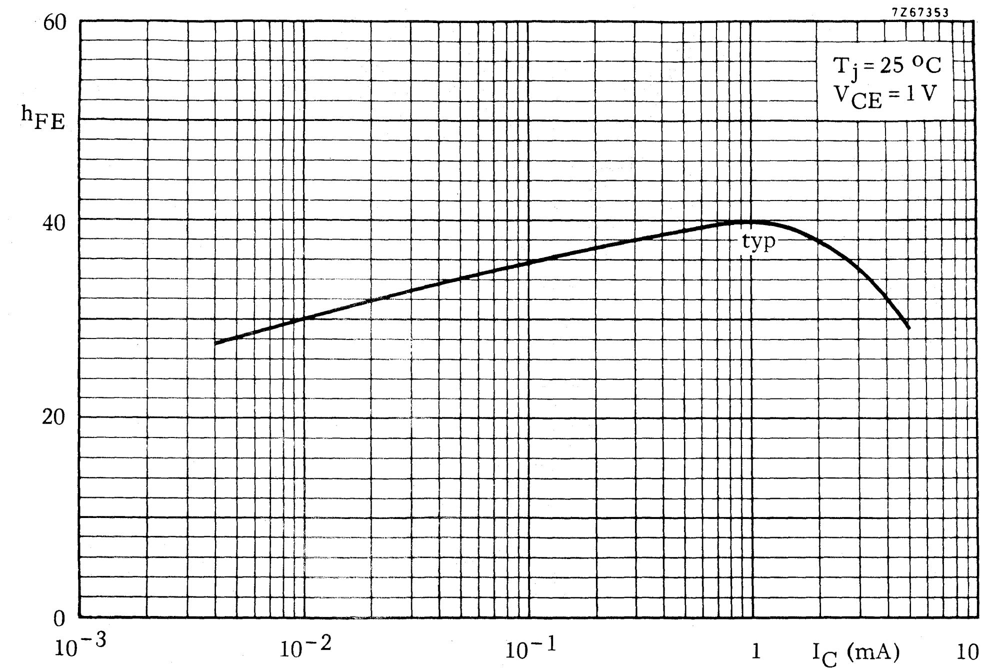


Fig. 3 V_{CE} = 1 V; T_j = 25 ^oC; typical values.

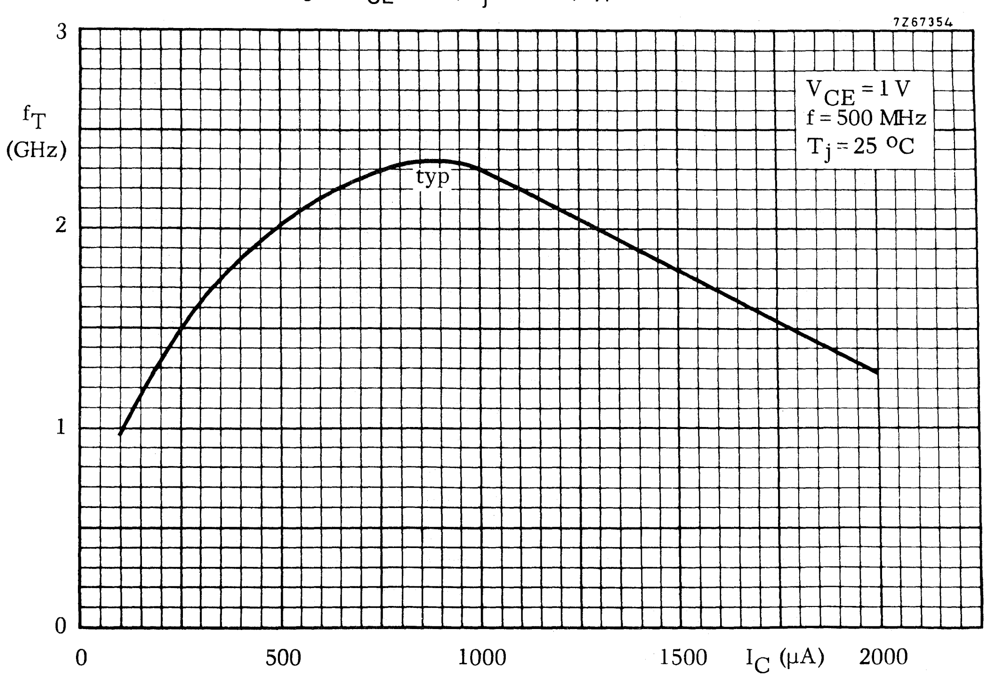


Fig. 4 V_{CE} = 1 V; f = 500 MHz; T_j = 25 ^oC; typical values.

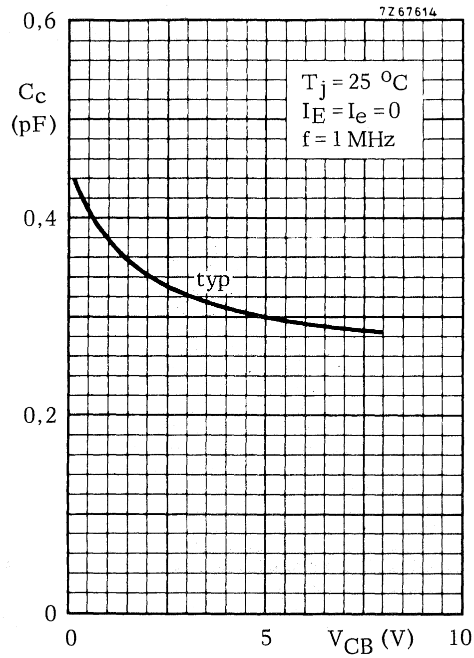


Fig. 5 $I_E = I_e = 0$; f = 1 MHz; T_j = 25 °C; typical values.

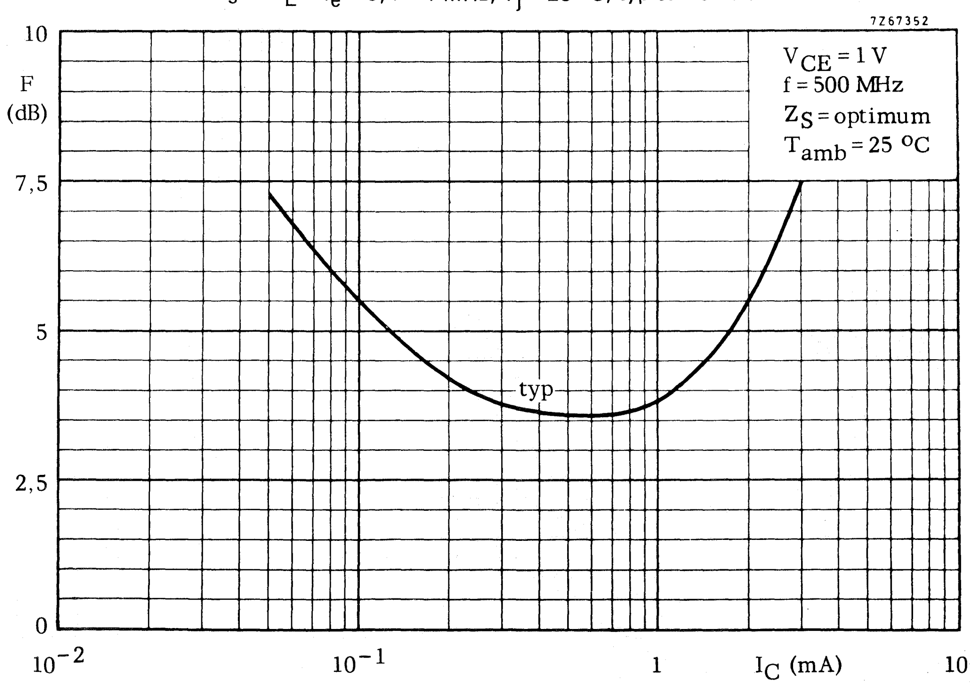


Fig. 6 V_{CE} = 1 V; f = 500 MHz; Z_S = opt.; T_{amb} = 25 °C; typical values.

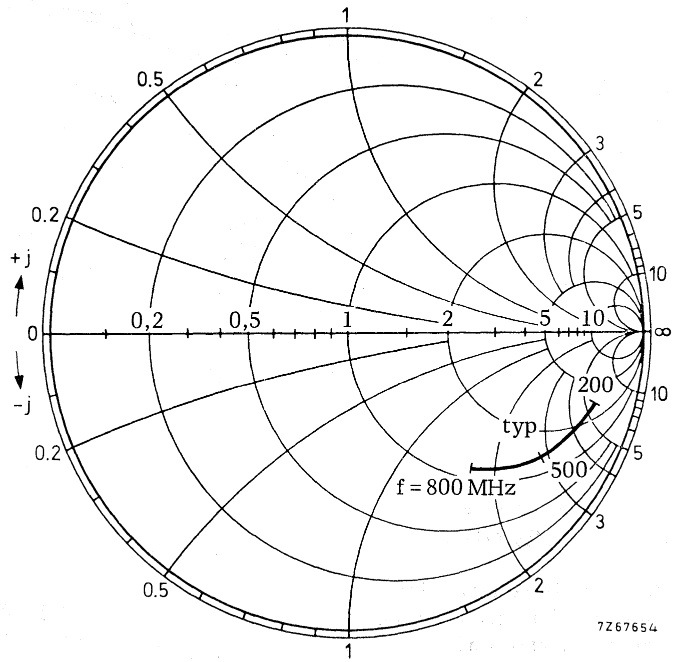


Fig. 7 V_{CE} = 1 V; I_C = 1 mA; T_{amb} = 25 °C; typical values.

Input impedance derived from input reflection coefficient s_{ie} coordinates in ohm x 50

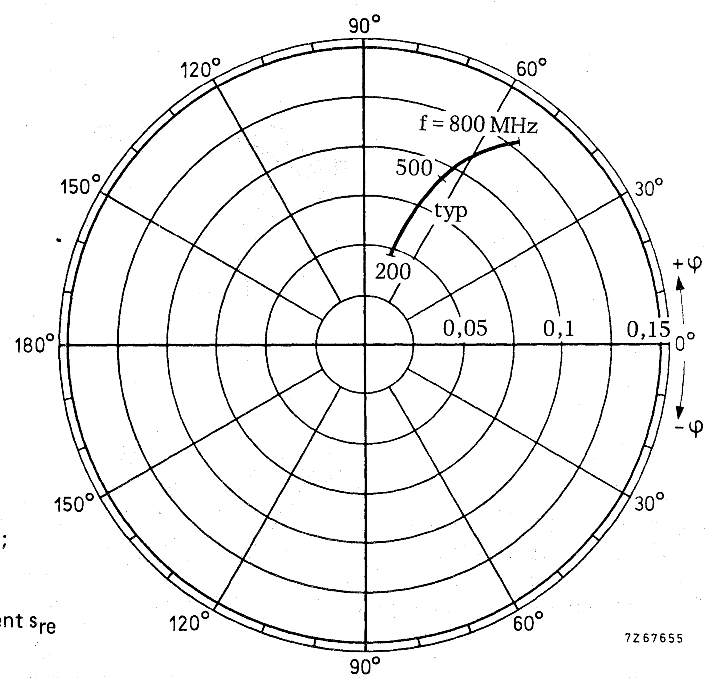


Fig. 8 V_{CE} = 1 V; I_C = 1 mA; T_{amb} = 25 °C; typical values.

Reverse transmission coefficient s_{re}

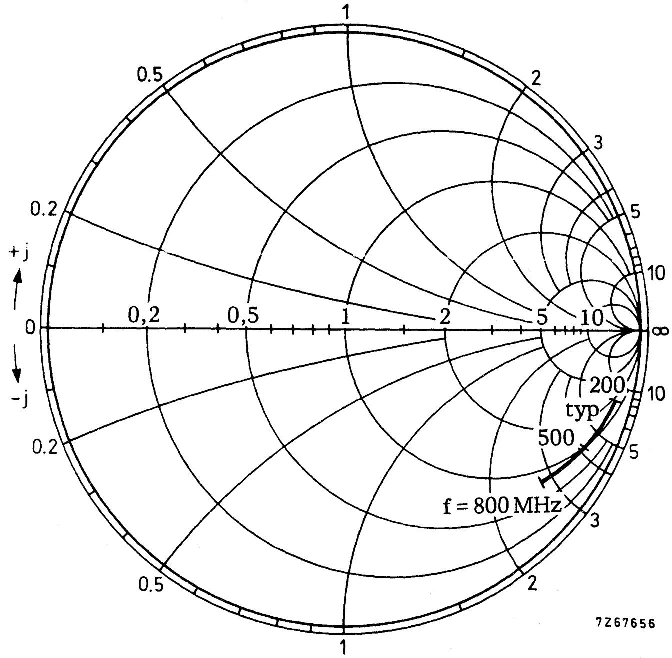


Fig. 9 V_{CE} = 1 V; I_C = 1 mA; T_{amb} = 25 °C; typical values.

Output impedance derived from output reflection coefficient s_{oe} coordinates in ohm x 50

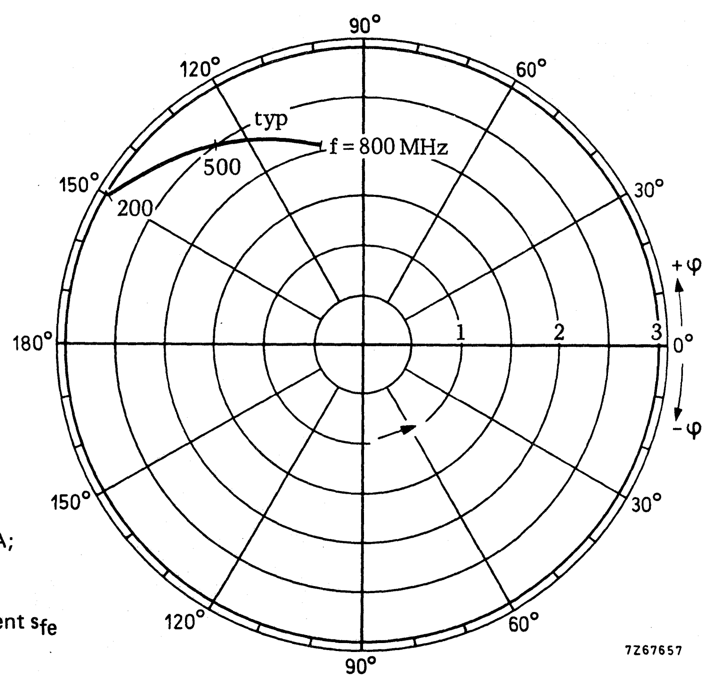


Fig. 10 V_{CE} = 1 V; I_C = 1 mA; T_{amb} = 25 °C; typical values.

Forward transmission coefficient s_{fe}

N-CHANNEL SILICON FET

N-channel silicon epitaxial planar junction field-effect transistor in a microminiature plastic envelope. The transistor is intended for low level general purpose amplifiers in thick and thin-film circuits.

QUICK REFERENCE DATA

Drain-source voltage	$\pm V_{DS}$	max.	25	V
Gate-source voltage (open drain)	$-V_{GSO}$	max.	25	V
Total power dissipation up to T_{amb} = 65 °C	P_{tot}	max.	250	mW
Drain current V_{DS} = 10 V; V_{GS} = 0	I_{DSS}	> <	0,2 1,5	mA mA
Transfer admittance (common source) I_D = 0,2 mA; V_{DS} = 10 V; f = 1 kHz	$\|y_{fs}\|$	>	0,5	mS
Equivalent noise voltage V_{DS} = 10 V; I_D = 200 μA; B = 0,6 to 100 Hz	V_n	<	0,5	μV

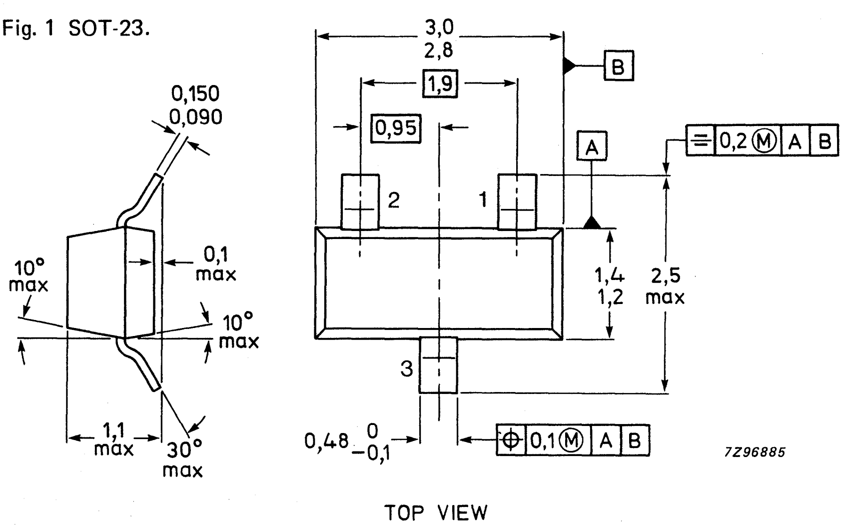
MECHANICAL DATA

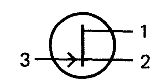
Dimensions in mm

Marking code

BFT46 = M3

Fig. 1 SOT-23.





See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	$\pm V_{DS}$	max.	25 V
Drain-gate voltage (open source)	V_{DGO}	max.	25 V
Gate-source voltage (open drain)	$-V_{GSO}$	max.	25 V
Drain current	I_D	max.	10 mA
Gate current	I_G	max.	5 mA
Total power dissipation up to T_{amb} = 65 °C**	P_{tot}	max.	250 mW
Storage temperature range	T_{stg}		–65 to +175 °C
Junction temperature	T_j	max.	175 °C

THERMAL CHARACTERISTICS*

$$R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a} = \frac{T_j - T_{amb}}{P}$$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	60 K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280 K/W
From soldering points to ambient**	$R_{th\ s\text{-}a}$	=	90 K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Gate cut-off current $-V_{GS}$ = 10 V; V_{DS} = 0	$-I_{GSS}$	<	0,2 nA
Drain current ** V_{DS} = 10 V; V_{GS} = 0	I_{DSS}	> <	0,2 mA 1,5 mA
Gate-source voltage I_D = 50 μA; V_{DS} = 10 V	$-V_{GS}$	> <	0,1 V 1,0 V
Gate-source cut-off voltage I_D = 0,5 nA; V_{DS} = 10 V	$-V_{(P)GS}$	<	1,2 V
y-parameters at f = 1 kHz; V_{DS} = 10 V; V_{GS} = 0; T_{amb} = 25 °C			
Transfer admittance	$\lvert y_{fs} \rvert$	>	1,0 mS
Output admittance	$\lvert y_{os} \rvert$	<	10 μS
V_{DS} = 10 V; I_D = 200 μA;			
Transfer admittance	$\lvert y_{fs} \rvert$	>	0,5 mS
Output admittance	$\lvert y_{os} \rvert$	<	5 μS

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

Input capacitance at f = 1 MHz; V_{DS} = 10 V; V_{GS} = 0; T_{amb} = 25 °C	C_{is}	$<$	5 pF
Feedback capacitance at f = 1 MHz; V_{DS} = 10 V; V_{GS} = 0; T_{amb} = 25 °C	C_{rs}	$<$	1,5 pF
Equivalent noise voltage V_{DS} = 10 V; I_D = 200 μA; T_{amb} = 25 °C B = 0,6 to 100 Hz	V_n	$<$	0,5 μV

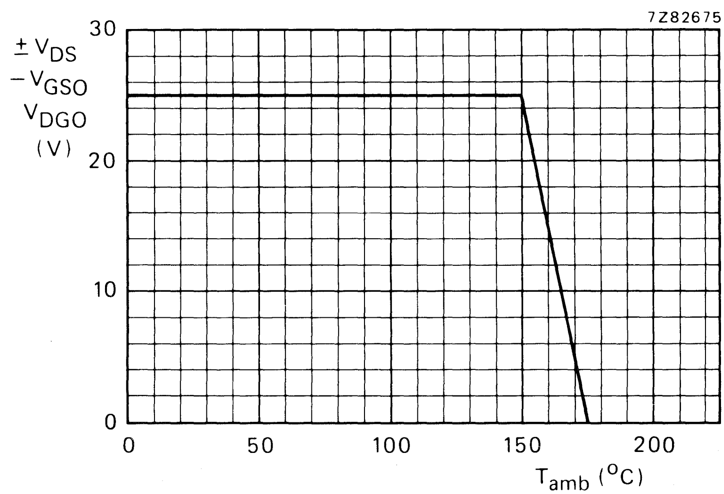


Fig. 2 Voltage derating curve.

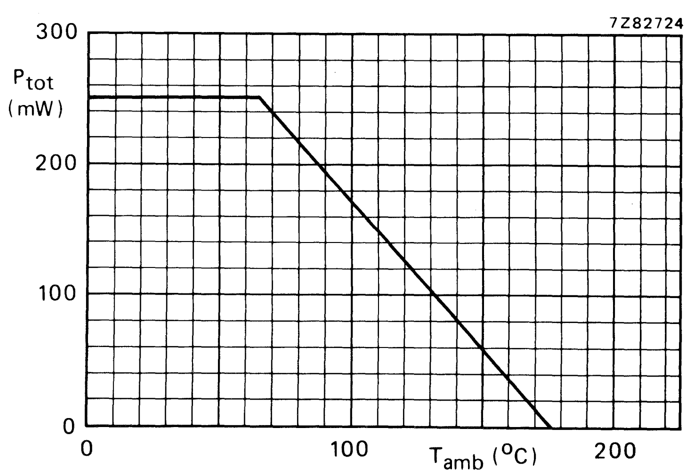


Fig. 3 Power derating curve.

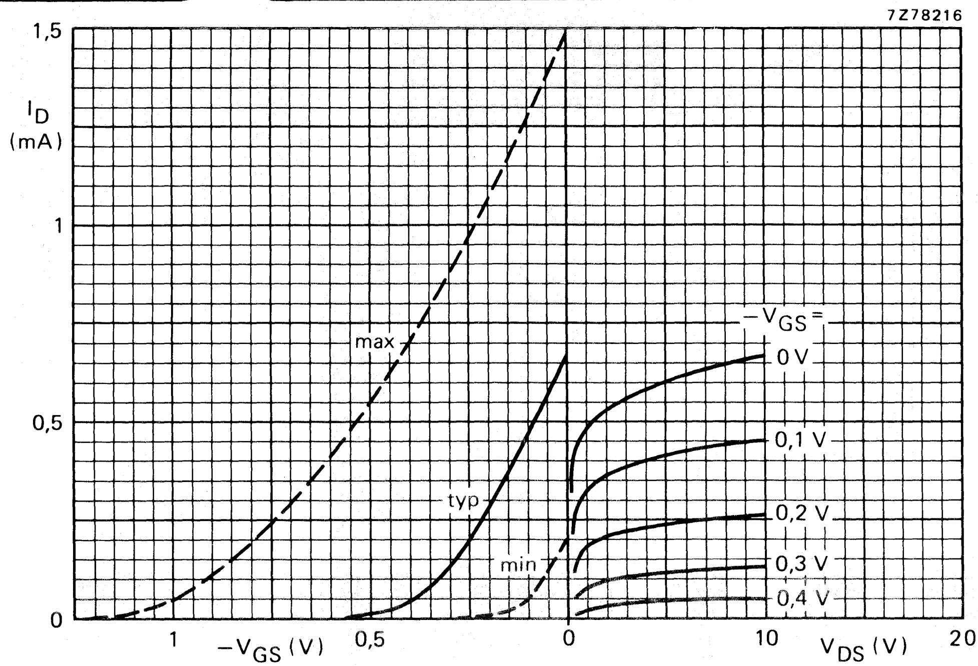


Fig. 4 Typical values. V_{DS} = 10 V; T_j = 25 °C.

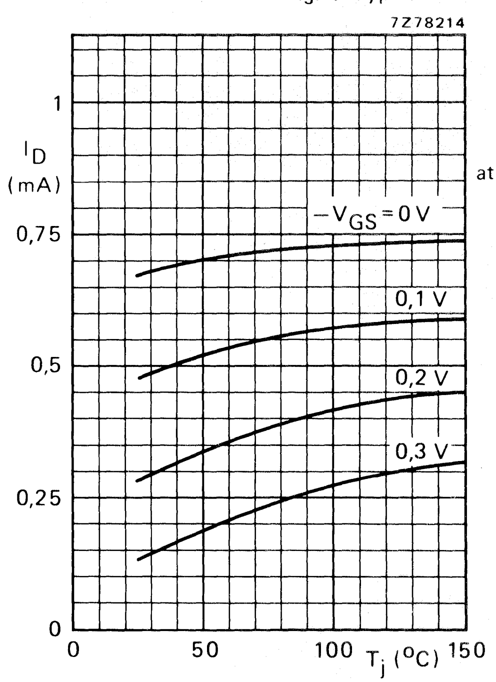


Fig. 5 Typical values. V_{DS} = 10 V.

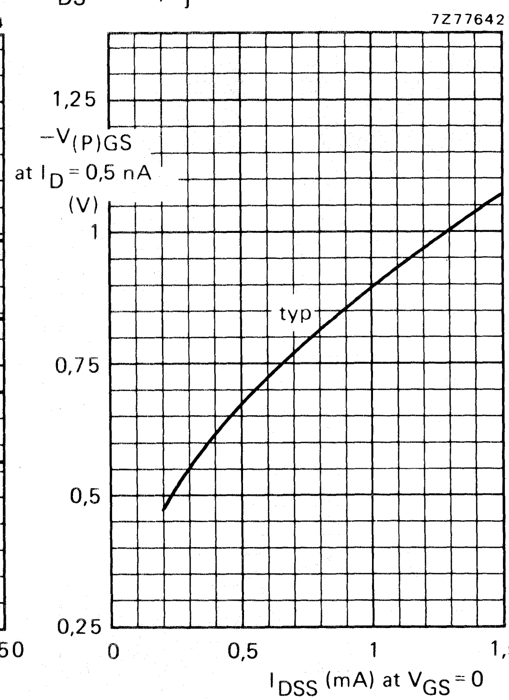


Fig. 6 Correlation between $-V_{(P)GS}$ and I_{DSS}.
V_{DS} = 10 V; T_j = 25 °C.

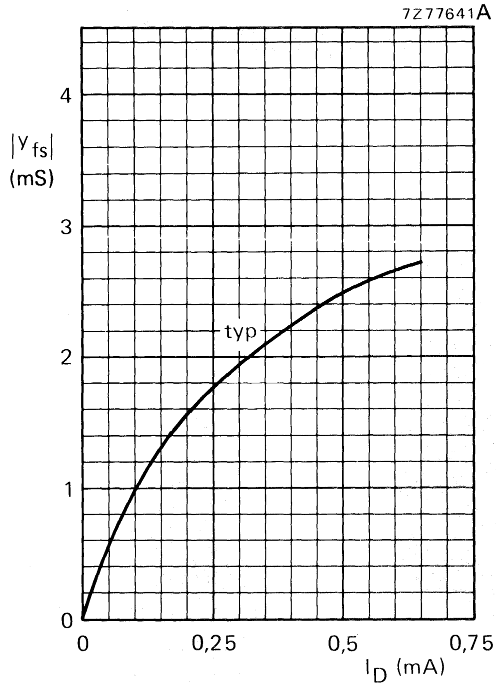


Fig. 7.

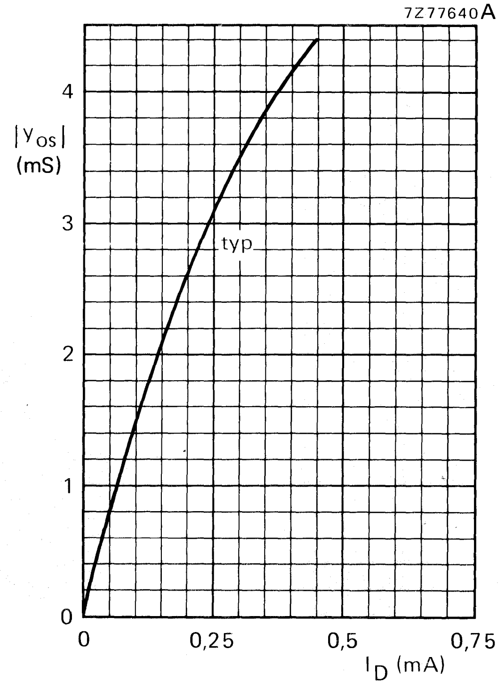


Fig. 8.

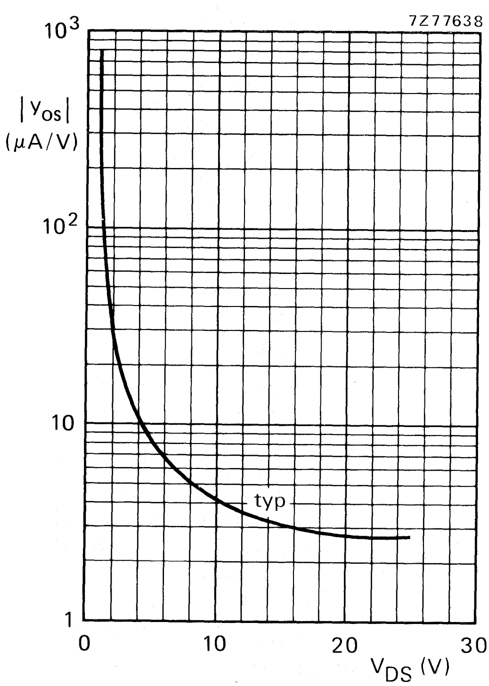


Fig. 9.

Fig. 7 $|y_{fs}|$ versus I_D.
V_{DS} = 10 V; f = 1 kHz; T_{amb} = 25 °C.

Fig. 8 $|y_{os}|$ versus I_D.
V_{DS} = 10 V; f = 1 kHz; T_{amb} = 25 °C.

Fig. 9 $|y_{os}|$ versus V_{DS}.
I_D = 0,4 mA; f = 1 kHz; T_{amb} = 25 °C.

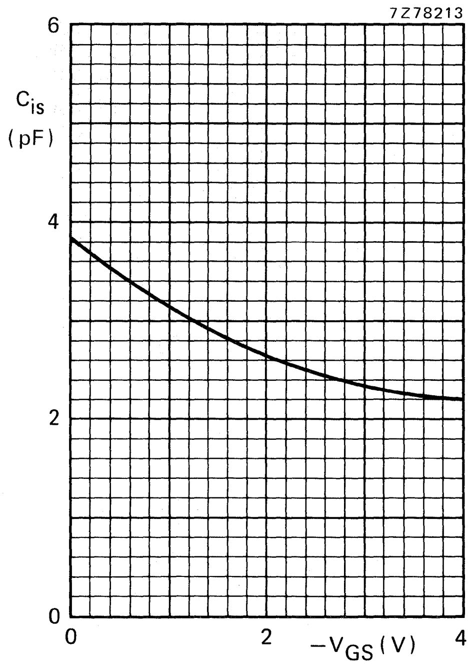


Fig. 10.

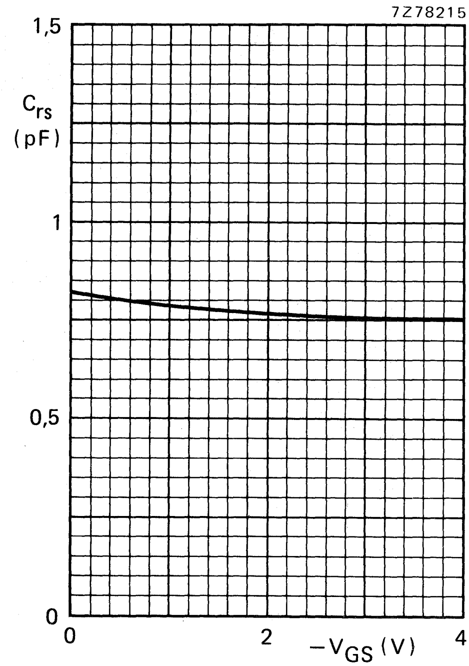


Fig. 11.

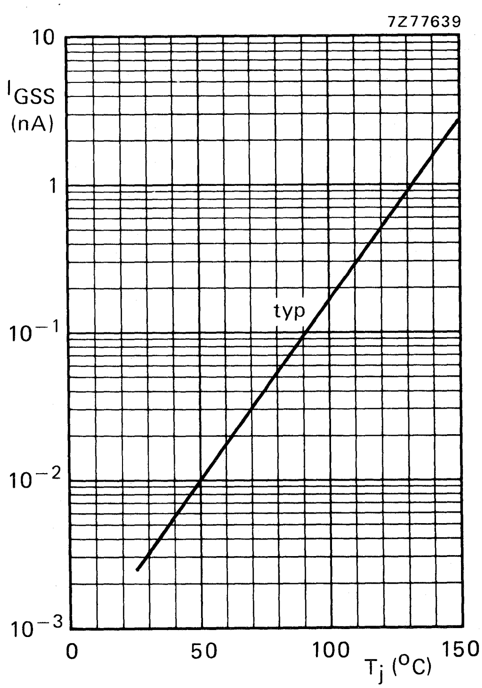


Fig. 12.

Fig.10 Typical values.
V_{DS} = 10 V, T_{amb} = 25 °C.

Fig.11 Typical values.
V_{DS} = 10 V, T_{amb} = 25 °C.

Fig.12 I_{GSS} versus T_j.
$-V_{GSS}$ = 10V; V_{DS} = 0.

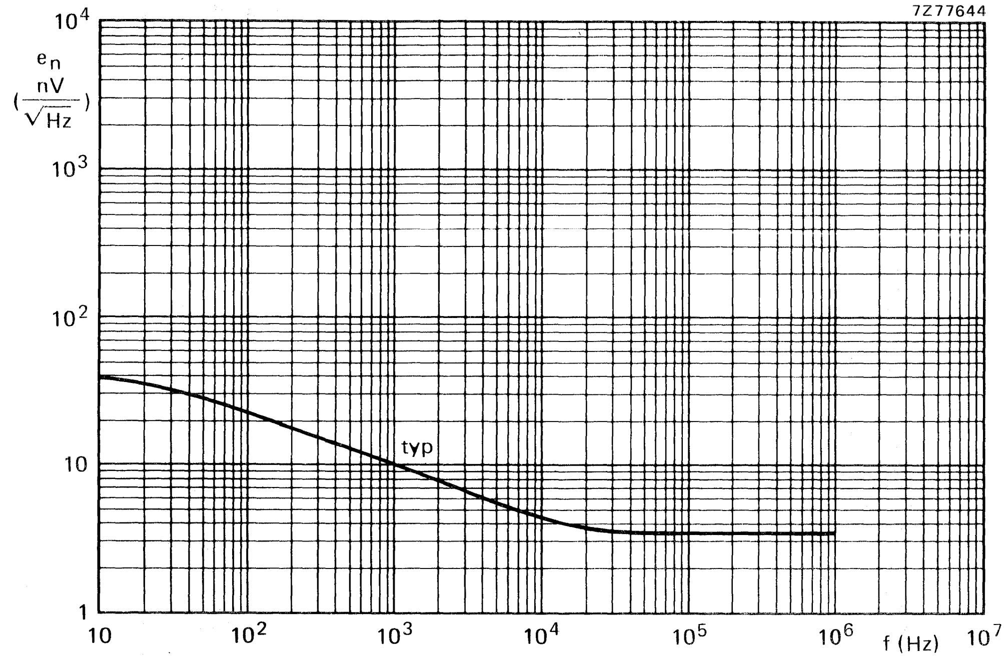


Fig. 13 V_{DS} = 10 V; I_D = 0,2 mA; T_{amb} = 25 °C.

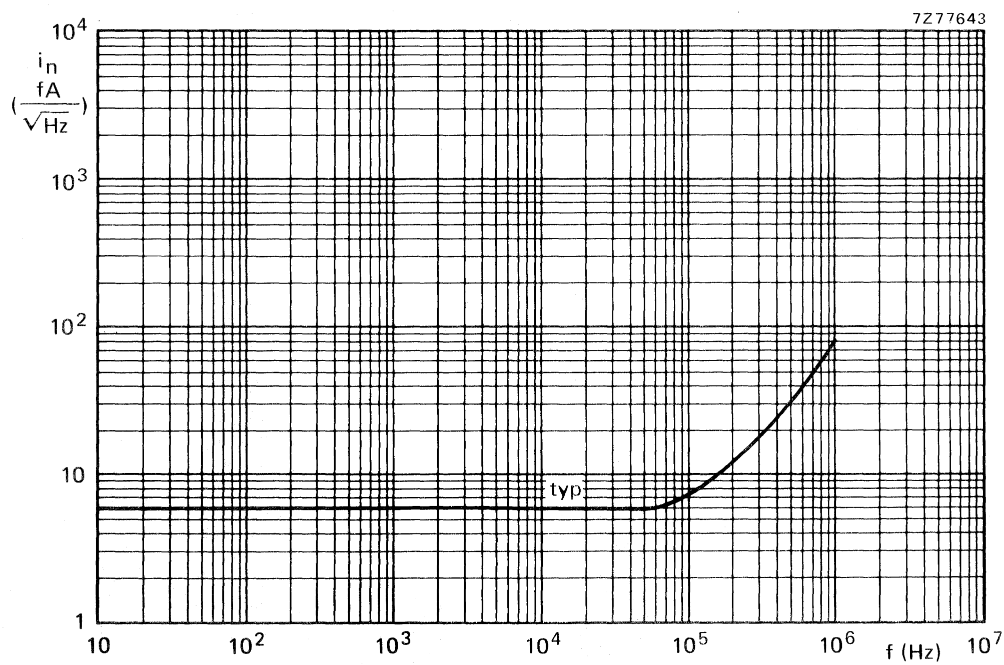


Fig. 14 V_{DS} = 10 V; I_D = 0,2 mA; T_{amb} = 25 °C.

SILICON PLANAR EPITAXIAL TRANSISTORS

P-N-P transistor in a microminiature plastic envelope. It is primarily intended for use in u.h.f. and microwave amplifiers in thick and thin-film circuits, such as in aerial amplifiers, radar systems, oscilloscopes, spectrum analysers, etc.

The transistor features low intermodulation distortion and high power gain; thanks to its very high transition frequency, it also has excellent wideband properties and low noise up to high frequencies.

N-P-N complements are BFR92 and BFR92A.

QUICK REFERENCE DATA

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	20	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	15	V
Collector current (d.c.)	$-I_C$	max.	25	mA
Total power dissipation up to T_{amb} = 60 °C	P_{tot}	max.	200	mW
Junction temperature	T_j	max.	150	°C
Transition frequency at f = 500 MHz $-I_C$ = 14 mA; $-V_{CE}$ = 10 V	f_T	typ.	5	GHz
Feedback capacitance at f = 1 MHz $-I_C$ = 2 mA; $-V_{CE}$ = 10 V; T_{amb} = 25 °C	C_{re}	typ.	0,7	pF
Noise figure at optimum source impedance $-I_C$ = 2 mA; $-V_{CE}$ = 10 V; f = 500 MHz; T_{amb} = 25 °C	F	typ.	2,7	dB
Max. unilateral power gain $-I_C$ = 14 mA; $-V_{CE}$ = 10 V; f = 500 MHz; T_{amb} = 25 °C	G_{UM}	typ.	18	dB
Intermodulation distortion at T_{amb} = 25 °C $-I_C$ = 14 mA; $-V_{CE}$ = 10 V; R_L = 75 Ω; V_o = 150 mV $f_{(p+q-r)}$ = 493,25 MHz	d_{im}	typ.	−60	dB

MECHANICAL DATA

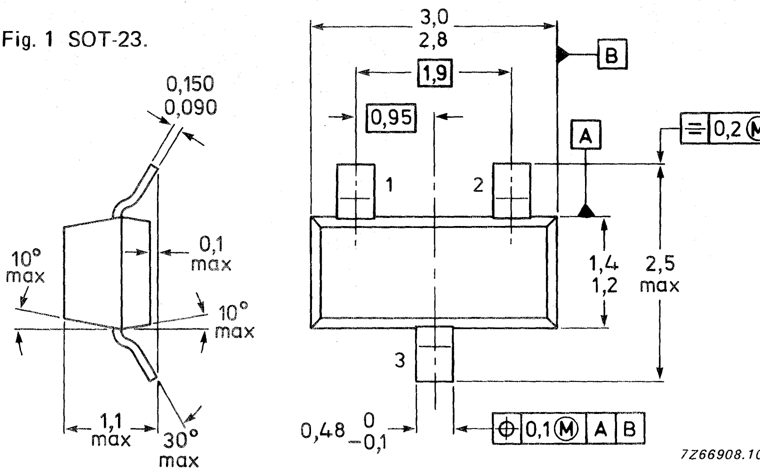
(See next page).

See also *Soldering recommendations.*

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-23.

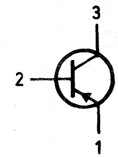


TOP VIEW

If required, the R-version (reverse pinning) is available on request.

Marking code

BFT92 = W1



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	20	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	15	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	2	V
Collector current (d.c.)	$-I_C$	max.	25	mA
Collector current (peak value; f > 1 MHz)	$-I_{CM}$	max.	35	mA
Total power dissipation up to T_{amb} = 60 °C **	P_{tot}	max.	200	mW
Storage temperature	T_{stg}	−65 to + 150		°C
Junction temperature	T_j	max.	150	°C

THERMAL CHARACTERISTICS *

$$T_j = P\,(R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	60	K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280	K/W
From soldering points to ambient **	$R_{th\ s\text{-}a}$	=	90	K/W

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current $I_E = 0$; $-V_{CB} = 10$ V	$-I_{CBO}$	max.	50	nA
D.C. current gain $-I_C = 14$ mA; $-V_{CE} = 10$ V	h_{FE}	min. typ.	20 50	
Transition frequency at f = 500 MHz $-I_C = 14$ mA; $-V_{CE} = 10$ V	f_T	typ.	5,0	GHz
Collector capacitance at f = 1 MHz $I_E = I_e = 0$; $-V_{CB} = 10$ V	C_c	typ.	0,75	pF
Emitter capacitance at f = 1 MHz $I_C = I_c = 0$; $-V_{EB} = 0{,}5$ V	C_e	typ.	0,8	pF

T_{amb} = 25 °C

Feedback capacitance at f = 1 MHz $-I_C = 2$ mA; $-V_{CE} = 10$ V	C_{re}	typ.	0,7	pF
Noise figure at optimum source impedance * $-I_C = 2$ mA; $-V_{CE} = 10$ V; f = 500 MHz	F	typ.	2,7	dB

Max. unilateral power gain (s_{re} assumed to be zero)

$$G_{UM} = 10 \log \frac{|s_{fe}|^2}{(1 - |s_{ie}|^2)(1 - |s_{oe}|^2)}$$

$-I_C = 14$ mA; $-V_{CE} = 10$ V; f = 500 MHz	G_{UM}	typ.	18,0	dB

Output voltage at $d_{im} = -60$ dB (see Fig. 2)
(DIN 45004B, par. 6.3.: 3-tone)
$-I_C = 14$ mA; $-V_{CE} = 10$ V; $R_L = 75\ \Omega$
$V_p = V_o$ at $d_{im} = -60$ dB; $f_p = 495{,}25$ MHz
$V_q = V_o$ −6 dB ; $f_q = 503{,}25$ MHz
$R_r = V_o$ −6 dB ; $f_r = 505{,}25$ MHz
measured at $f_{(p+q-r)} = 493{,}25$ MHz — V_o typ. 150 mV

* Crystal mounted in SOT-37 envelope.

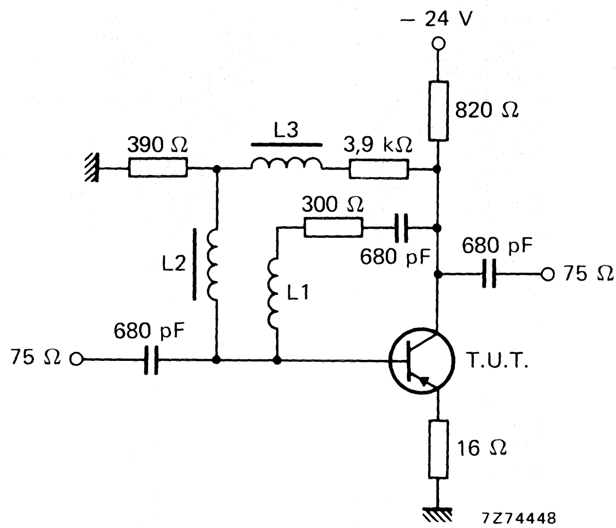


Fig. 2 Intermodulation test circuit.

L1 = 4 turns Cu wire (0,35 mm); winding pitch 1 mm; int. dia. 4 mm.
L2 = L3 = 5 μH (catalogue number: 3122 108 20150).

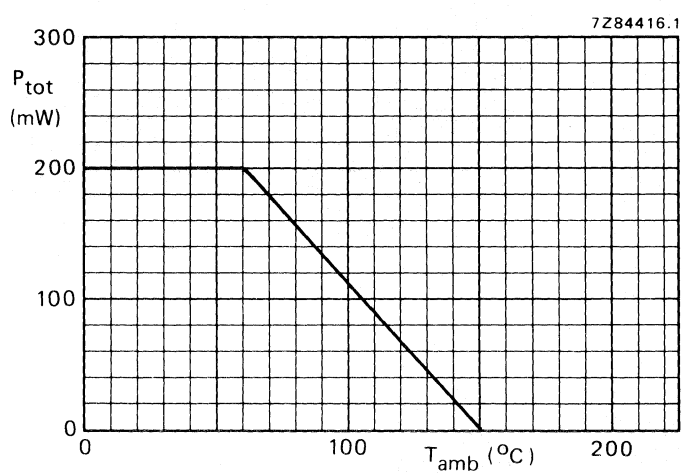


Fig. 3 Power derating curve.

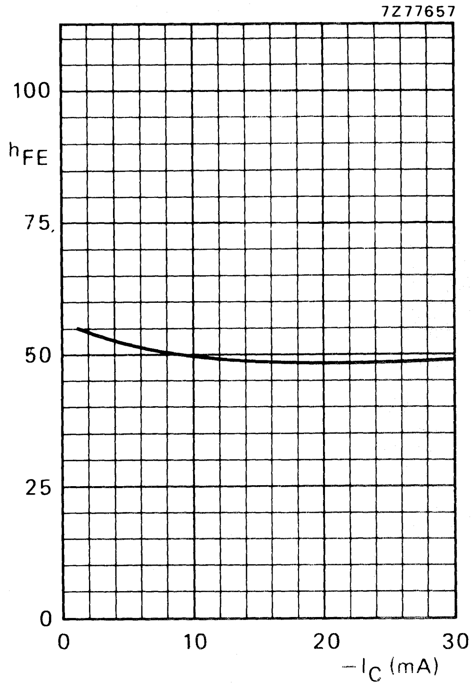


Fig. 4 $-V_{CE}$ = 10 V; T_j = 25 °C; typical values.

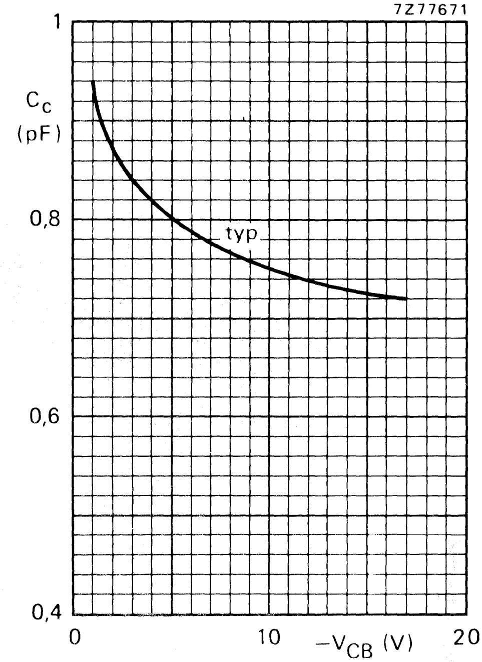


Fig. 5 $I_E = I_e = 0$; T_j = 25 °C; f = 1 MHz; typical values.

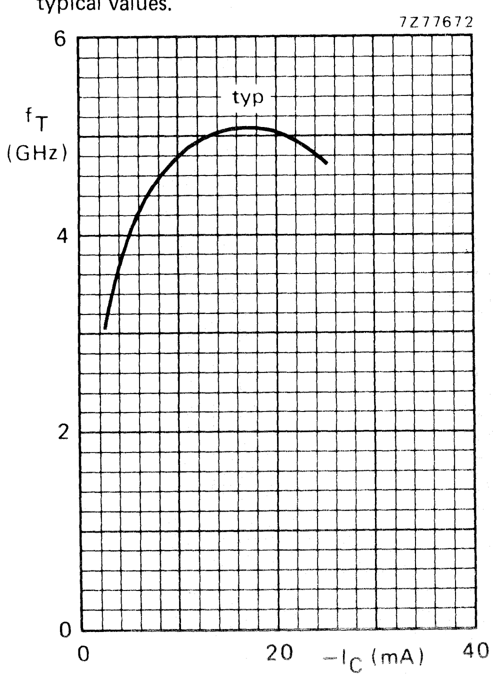


Fig. 6 $-V_{CE}$ = 10 V; f = 500 MHz; T_j = 25 °C; typical values.

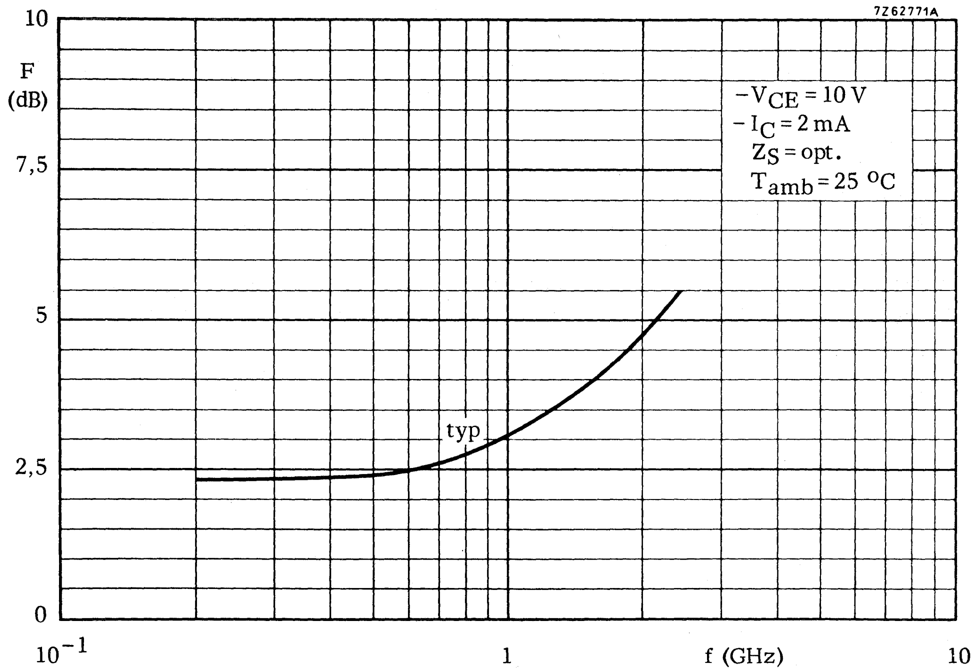


Fig. 7 $-V_{CE}$ = 10 V; $-I_C$ = 2 mA; Z_S = opt.; T_{amb} = 25 °C; typical values.

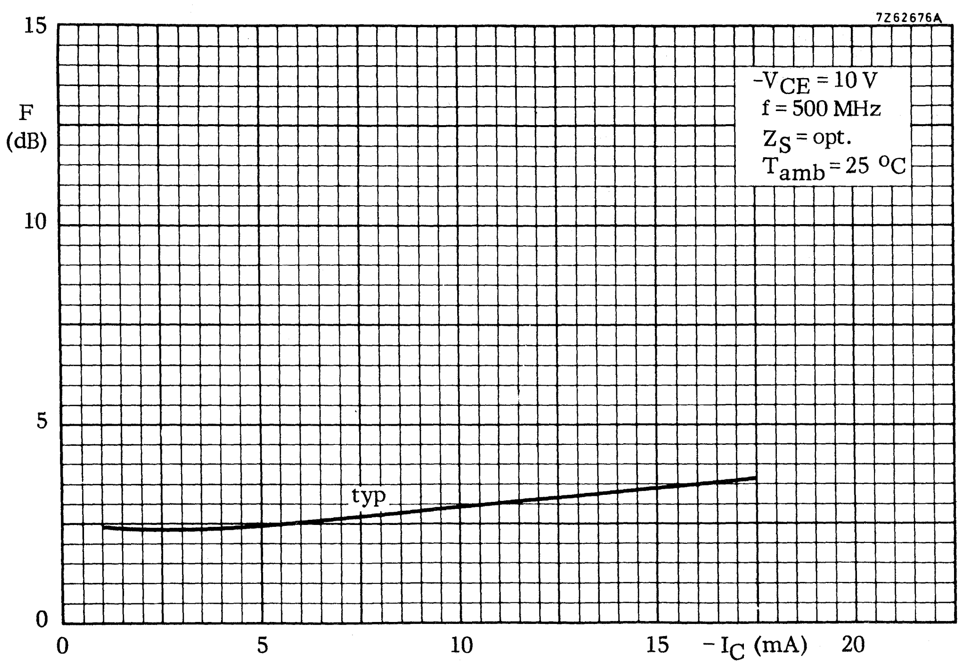


Fig. 8 $-V_{CE}$ = 10 V; f = 500 MHz; Z_S = opt.; T_{amb} = 25 °C; typical values.

P-N-P 1 GHz WIDEBAND TRANSISTOR

P-N-P transistor in a plastic SOT-23 envelope. It is primarily intended for use in u.h.f. and microwave amplifiers in thick and thin-film circuits, such as in aerial amplifiers, radar systems, oscilloscopes, spectrum analyses, etc.

The transistor features low intermodulation distortion and high power gain; thanks to its very high transition frequency, it also has excellent wideband properties and low noise up to high frequencies.

N-P-N complements are BFR93 and BFR93A.

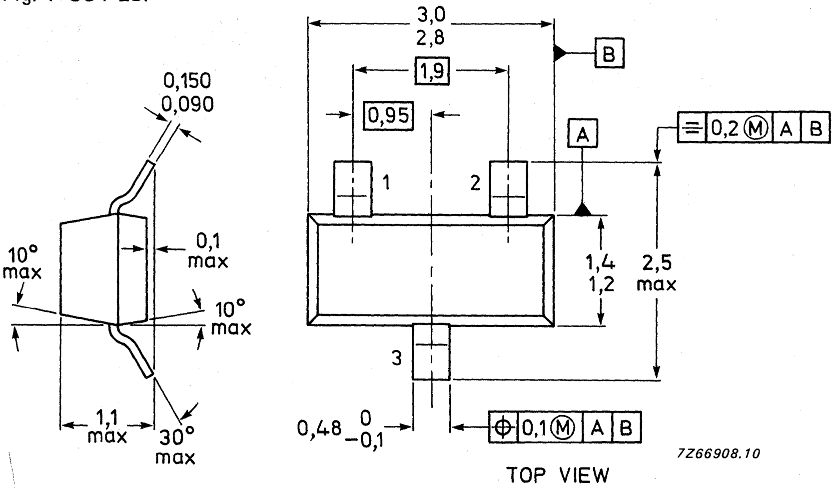
QUICK REFERENCE DATA

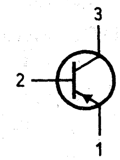
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	15	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	12	V
Collector current (d.c.)	$-I_C$	max.	35	mA
Total power dissipation up to T_{amb} = 60 °C	P_{tot}	max.	200	mW
Junction temperature	T_j	max.	150	°C
Transition frequency at f = 500 MHz $-I_C$ = 30 mA; $-V_{CE}$ = 5 V	f_T	typ.	5,0	GHz
Feedback capacitance at f = 1 MHz $-I_C$ = 2 mA; $-V_{CE}$ = 5 V	C_{re}	typ.	1,0	pF
Noise figure at optimum source impedance $-I_C$ = 2 mA; $-V_{CE}$ = 5 V; f = 500 MHz	F	typ.	2,4	dB
Max. unilateral power gain $-I_C$ = 30 mA; $-V_{CE}$ = 5 V; f = 500 MHz	G_{UM}	typ.	16,5	dB
Output voltage at d_{im} = −60 dB $-I_C$ = 30 mA; $-V_{CE}$ = 5 V; R_L = 75 Ω $f_{(p+q-r)}$ = 493,25 MHz	V_o	typ.	300	mV

MECHANICAL DATA Dimensions in mm **Marking code**

Fig. 1 SOT-23.

BFT93 = X1





If required, the R-version (reverse pinning) is available on request.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	15	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	12	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	2	V
Collector current (d.c.)	$-I_C$	max.	35	mA
Collector current (peak value; f > 1 MHz)	$-I_{CM}$	max.	50	mA
Total power dissipation up to T_{amb} = 60 °C **	P_{tot}	max.	200	mW
Storage temperature	T_{stg}	−65 to + 150		°C
Junction temperature	T_j	max.	150	°C

THERMAL CHARACTERISTICS *

$T_j = P \times (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	60	K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280	K/W
From soldering points to ambient **	$R_{th\ s\text{-}a}$	=	90	K/W

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current $I_E = 0; -V_{CB} = 5$ V	$-I_{CBO}$	max.	50	nA
D.C. current gain $-I_C = 30$ mA; $-V_{CE} = 5$ V	h_{FE}	min. typ.	20 50	
Transition frequency at f = 500 MHz $-I_C = 30$ mA; $-V_{CE} = 5$ V	f_T	typ.	5,0	GHz
Collector capacitance at f = 1 MHz $I_E = I_e = 0; -V_{CB} = 10$ V	C_c	typ.	0,95	pF
Emitter capacitance at f = 1 MHz $I_C = I_c = 0; -V_{EB} = 0,5$ V	C_e	typ.	1,8	pF
T_{amb} = 25 °C				
Feedback capacitance at f = 1 MHz $-I_C = 2$ mA; $-V_{CE} = 5$ V	C_{re}	typ.	1,0	pF
Noise figure at optimum source impedance * $-I_C = 2$ mA; $-V_{CE} = 5$ V; f = 500 MHz	F	typ.	2,4	dB
Max. unilateral power gain (s_{re} assumed to be zero) $G_{UM} = 10 \log \frac{\lvert s_{fe}\rvert^2}{(1 - \lvert s_{ie}\rvert^2)(1 - \lvert s_{oe}\rvert^2)}$ $-I_C = 30$ mA; $-V_{CE} = 5$ V; f = 500 MHz	G_{UM}	typ.	16,5	dB
Output voltage at $d_{im} = -60$ dB (see Fig. 2) $-I_C = 30$ mA; $-V_{CE} = 5$ V; $R_L = 75\ \Omega$ $V_p = V_o$ at $d_{im} = -60$ dB; $f_p = 495,25$ MHz $V_q = V_o - 6$ dB ; $f_q = 503,25$ MHz $V_r = V_o - 6$ dB ; $f_r = 505,25$ MHz measured at $f_{(p+q-r)} = 443,25$ MHz	V_o	typ.	300	mV

* Crystal mounted in SOT-37 envelope.

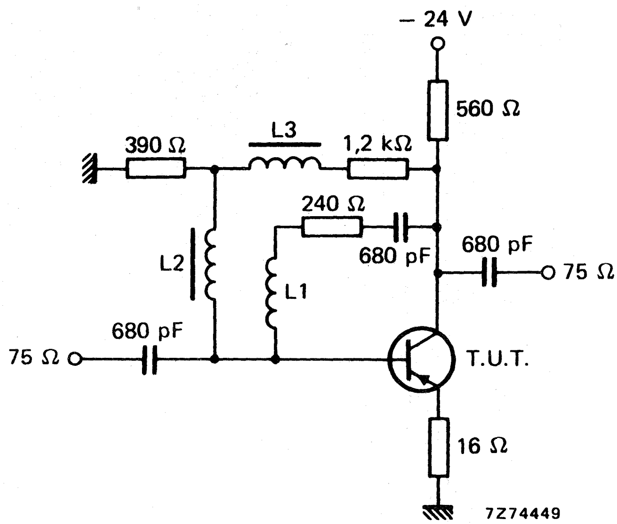


Fig. 2 Intermodulation test circuit.

L1 = 4 turns Cu wire (0,35); winding pitch 1 mm; int. dia. 4 mm.
L2 and L3 = 5 μH (catalogue number: 3122 108 20150).

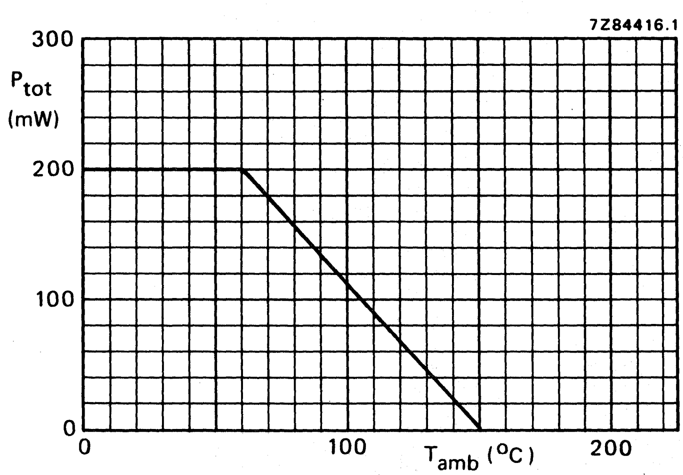


Fig. 3 Power derating curve.

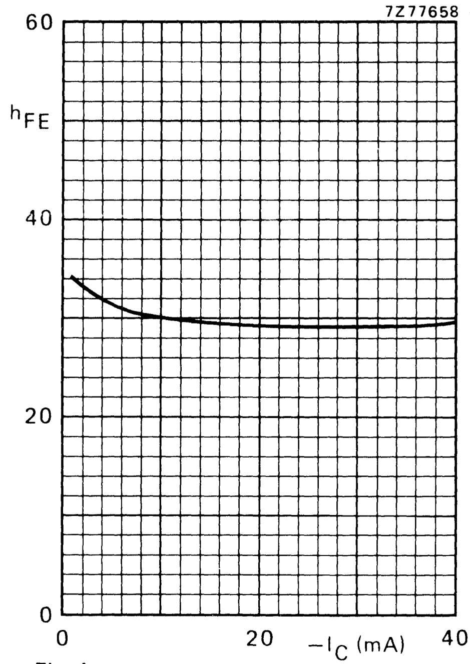


Fig. 4 $-V_{CE}$ = 5 V; T_j = 25 °C; typical values.

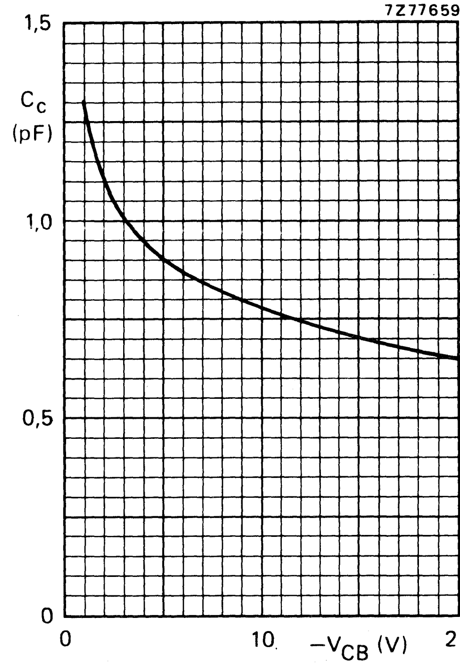


Fig. 5 $I_E = I_e = 0$; T_j = 25 °C; f = 1 MHz; typical values.

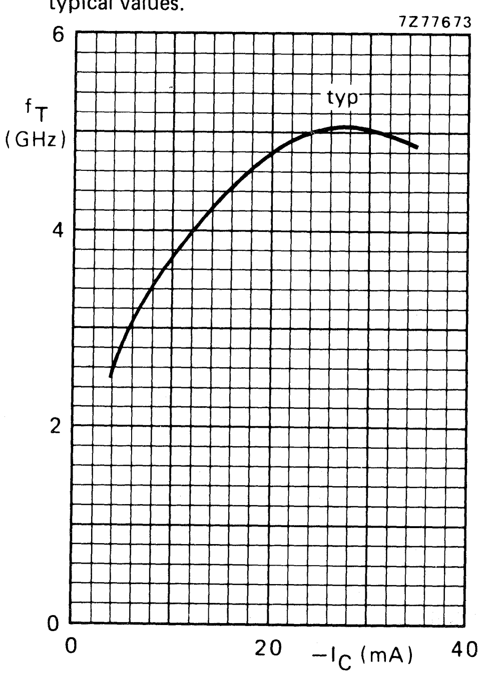


Fig. 6 $-V_{CE}$ = 5 V; T_j = 25 °C; f = 500 MHz; typical values.

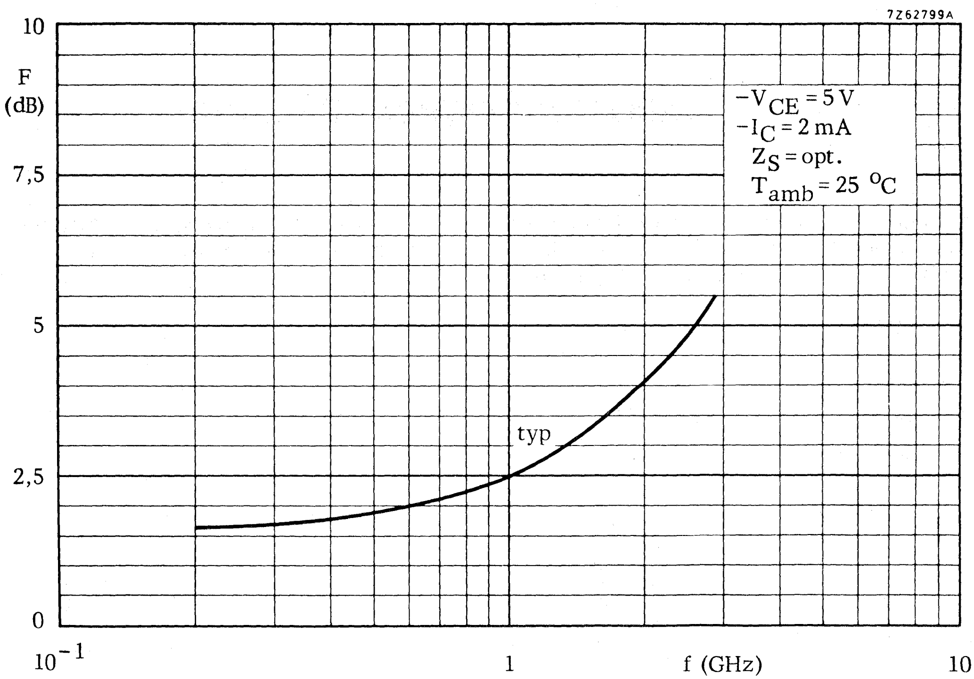


Fig. 7 $-V_{CE} = 5$ V; $-I_C = 2$ mA; Z_S = opt.; $T_{amb} = 25$ °C; typical values.

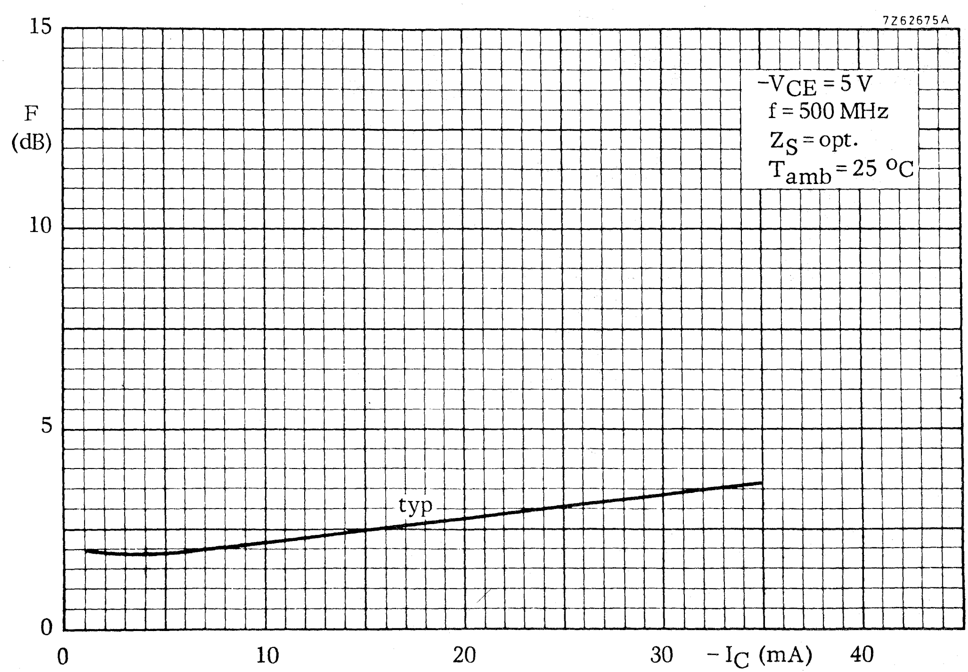


Fig. 8 $-V_{CE} = 5$ V; f = 500 MHz; Z_S = opt.; $T_{amb} = 25$ °C; typical values.

PROGRAMMABLE UNIJUNCTION TRANSISTOR

Planar p-n-p-n trigger device in a microminiature plastic envelope intended for applications in thick and thin-film circuits. It is intended for use in switching applications such as motor control, oscillators, relay replacement, timers, pulse shaper, trigger device etc.

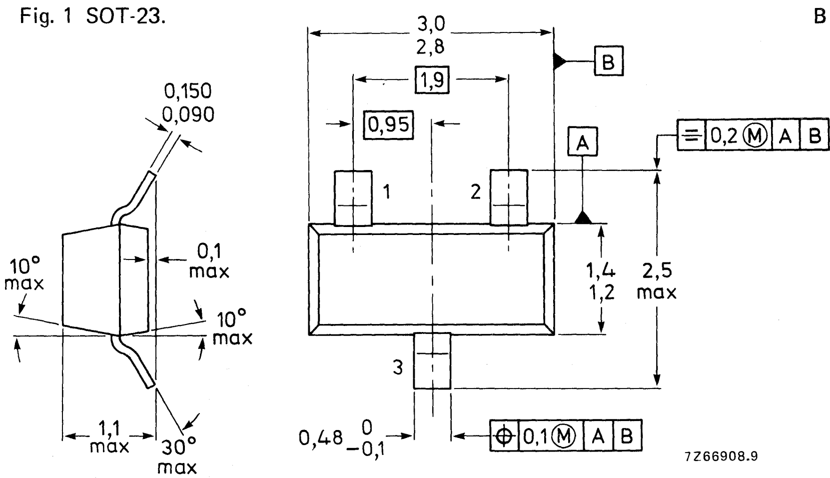
QUICK REFERENCE DATA

Gate-anode voltage	V_{GA}	max.	70 V
Anode current (d.c.) up to T_{amb} = 25 °C	I_A	max.	175 mA
Junction temperature	T_j	max.	150 °C
Peak point current V_S = 10 V; R_G = 10 kΩ	I_P	<	5 μA
Valley point current V_S = 10 V; R_G = 10 kΩ	I_V	>	30 μA

MECHANICAL DATA

Dimensions in mm

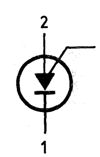
Fig. 1 SOT-23.



TOP VIEW

Marking code

BRY61 = A5



See also *Soldering Recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Gate-anode voltage	V_{GA}	max.	70 V
Anode current (d.c.) up to T_{amb} = 25 °C	I_A	max.	175 mA
Repetitive peak anode current t = 10 µs; δ = 0,01	I_{ARM}	max.	2,5 A
Non-repetitive peak anode current t = 10 µs; T_j = 150 °C	I_{ASM}	max.	3 A
Rate of rise of anode current up to I_A = 2,5 A	$\frac{dI_A}{dt}$	max.	20 A/µs
Storage temperature	T_{stg}		−65 to + 150 °C
Junction temperature	T_j	max.	150 °C
Total power dissipation up to T_{amb} = 25 °C**	P_{tot}	max.	275 mW

THERMAL CHARACTERISTICS*

$T_j = P \times (R_{th\,j\text{-}t} + R_{th\,t\text{-}s} + R_{th\,s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\,j\text{-}t}$	=	60 K/W
From tab to soldering points	$R_{th\,t\text{-}s}$	=	280 K/W
From soldering points to ambient**	$R_{th\,s\text{-}a}$	=	90 K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Peak point current (see Figs 2, 3 and 4) V_S = 10 V; R_G = 10 kΩ	I_P	<	5 µA
V_S = 10 V; R_G = 1 MΩ	I_P	<	1 µA
Valley point current (see also Figs 2, 3 and 4) V_S = 10 V; R_G = 10 kΩ	I_V	>	30 µA
V_S = 10 V; R_G = 1 MΩ	I_V	<	50 µA
Offset voltage (see Fig. 12) I_A = 0 (for V_P see Fig. 2; for V_S see Fig. 4)	V_{offset}	=	$V_P - V_S$ V

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

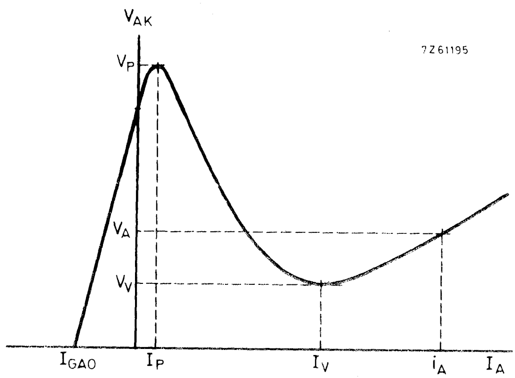


Fig. 2 See also Fig. 11.

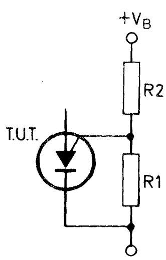


Fig. 3 BRY61 with "program" resistors R1 and R2.

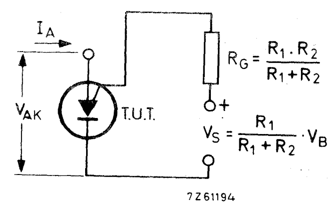


Fig. 4 Equivalent test circuit for characteristics testing.

Gate-anode leakage current (Fig. 5a) $I_K = 0$; $V_{GA} = 70$ V	I_{GAO}	<	10 nA
Gate-cathode leakage current (Fig. 5b) $V_{AK} = 0$; $V_{GK} = 70$ V	I_{GKS}	<	100 nA

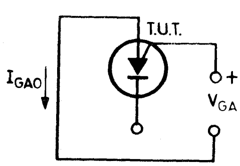


Fig. 5a.

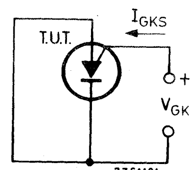


Fig. 5b.

Anode voltage			
I_A = 100 mA	V_A	<	1,4 V
I_A = 180 mA	V_A	<	1,6 V
Peak output voltage			
V_{AA} = 20 V; C = 200 nF (see Fig. 12)	V_{OM}	>	6 V
Rise time			
V_{AA} = 20 V; C = 10 nF (see Fig. 12)	t_r	<	80 ns

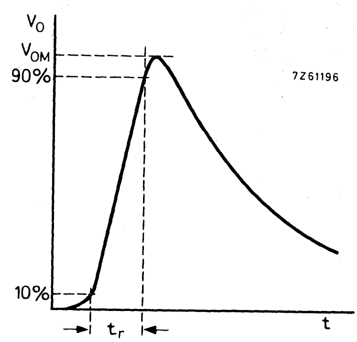


Fig. 6 Output voltage waveform.

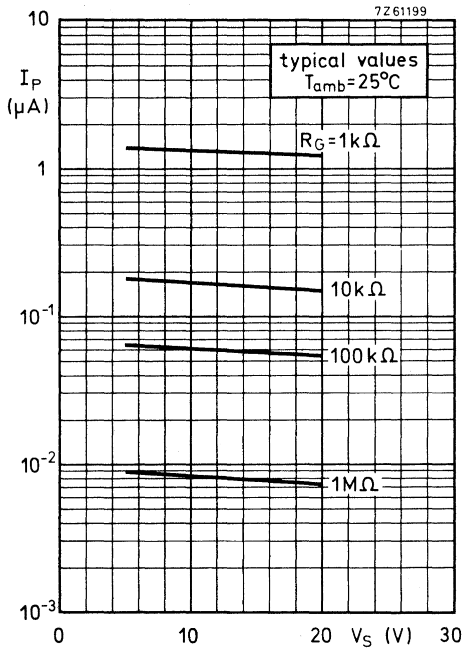


Fig. 7.

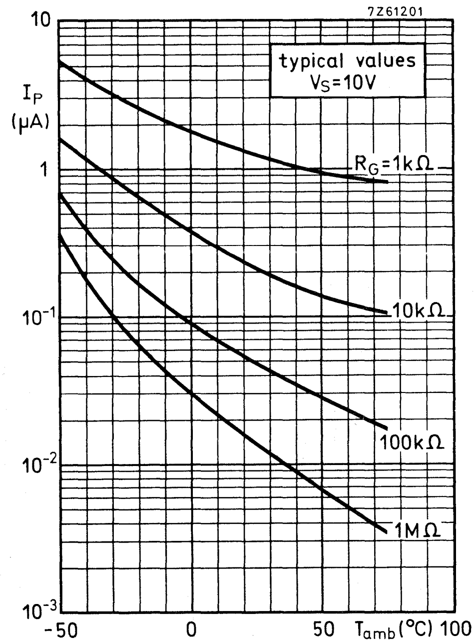


Fig. 8.

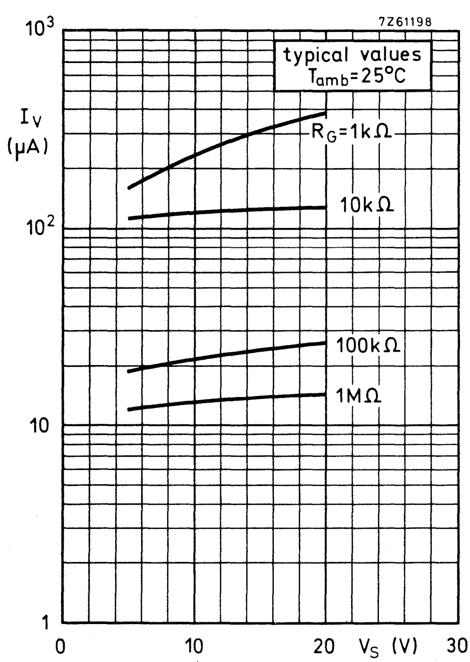


Fig. 9.

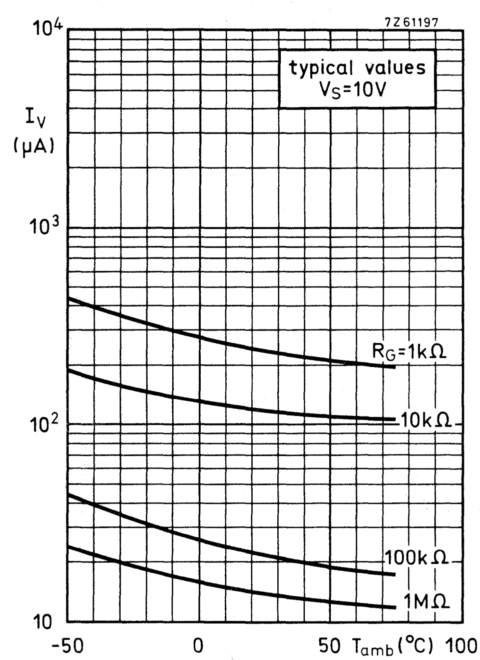


Fig. 10.

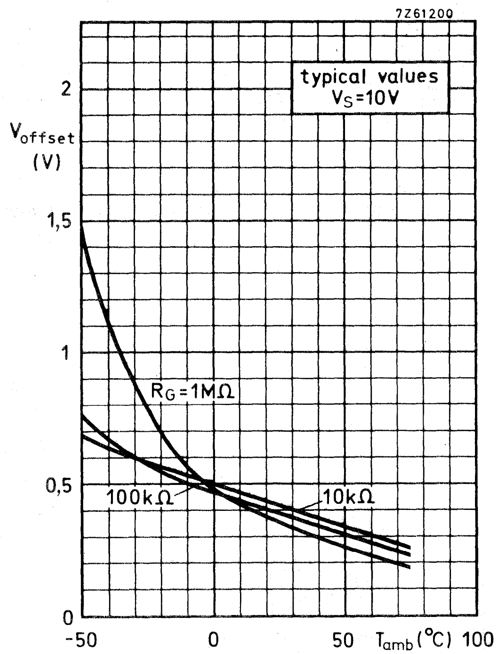

7Z61200
typical values
V_S=10V
V_{offset}
(V)
2
1,5
1
0,5
0
R_G=1MΩ
100kΩ
10kΩ
-50
0
50
T_{amb} (°C)
100

Fig. 11.

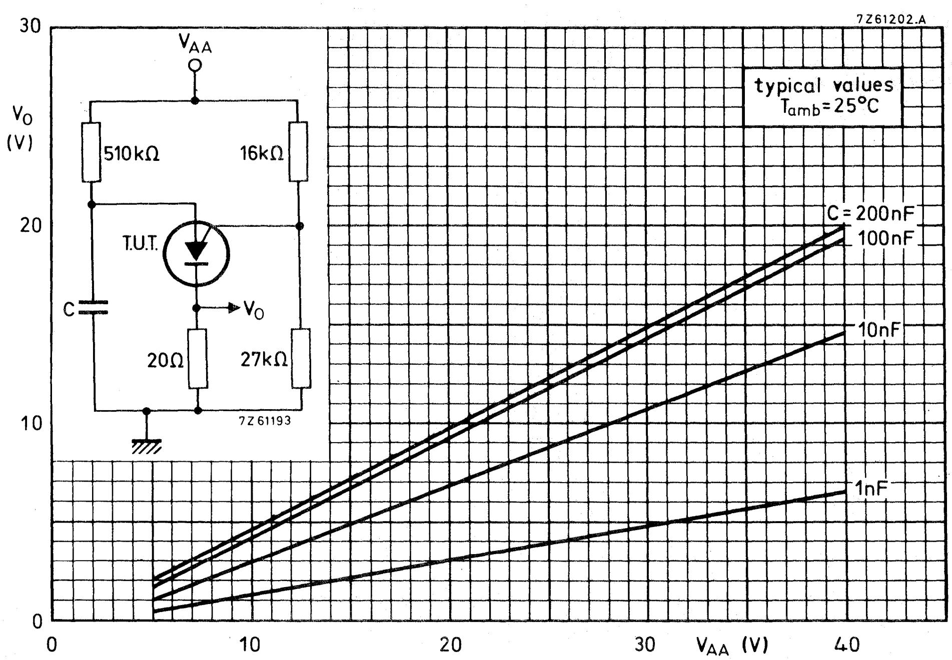

7Z61202.A
V_O
(V)
30
20
10
0
V_{AA}
510kΩ
16kΩ
T.U.T.
C
V_O
20Ω
27kΩ
7Z 61193
typical values
T_{amb}=25°C
C = 200nF
100nF
10nF
1nF
0
10
20
30
V_{AA} (V)
40

Fig. 12.

SILICON P-N-P-N PLANAR TETRODE THYRISTOR

Planar p-n-p-n trigger device in a microminiature plastic envelope. It is intended for use as a programmable trigger device (SCS = silicon controlled switch).

QUICK REFERENCE DATA

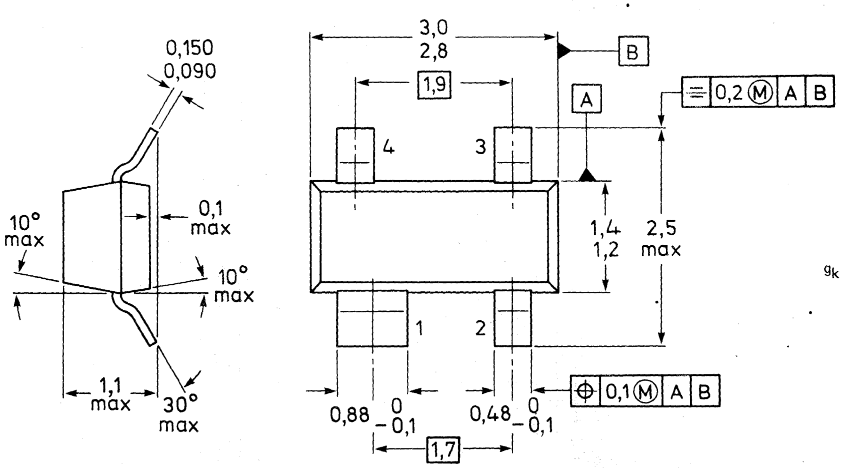
Anode gate – cathode voltage	$V_{ga\text{-}kR}$	max.	70	V
Anode gate – anode voltage (open cathode)	$V_{ga\text{-}aO}$	max.	70	V
Average anode current	$I_{A(AV)}$	max.	175	mA
Total power dissipation at T_{amb} = 25 °C	P_{tot}	max.	275	mW
Junction temperature	T_j	max.	150	°C
Gate-controlled turn-on time $R_{gk\text{-}k}$ = 1 kΩ	t_{gt}	<	0,25	µs
Circuit-commutated turn-off time $R_{gk\text{-}k}$ = 1 kΩ	t_q	<	5	µs

MECHANICAL DATA

Dimensions in mm

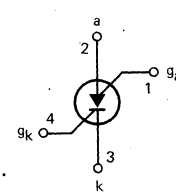
Marking code
BRY62 = A51

Fig. 1 SOT-143.



7Z85014.6

TOP VIEW



See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Transistor 1 (T1)

Collector-base voltage (open emitter)	V_{CBO}	max.	70	V
Collector-emitter voltage (R_{BE} = 10 kΩ)	V_{CEO}	max.	70	V
Emitter-collector voltage (I_{C1} = 0)	V_{EBO}	max.	5	V
Average collector current	$I_{C(AV)}$	max.	175	mA▲
Collector current (peak value)	I_{CM}	max.	175	mA**
Average emitter current	$I_{E(AV)}$	max.	175	mA
Emitter current (peak value) t_p = 10 µs; δ = 1%	I_{EM}	max.	2,5	A

Transistor 2 (T2)

Collector-base voltage (I_{E2} = 0)	$-V_{CBO}$	max.	70	V
Collector-emitter voltage (I_{B2} = 0)	$-V_{CEO}$	max.	70	V
Emitter-base voltage (I_{C2} = 0)	$-V_{EBO}$	max.	70	V
Emitter current (average)	$I_{E(AV)}$	max.	175	mA
Emitter current (peak value) t_p = 10 µs; δ = 1%	I_{EM}	max.	2,5	A
Reverse gate to cathode voltage	$V_{ga\text{-}kR}$	max.	70	V
Gate to anode voltage (open cathode)	$V_{ga\text{-}aO}$	max.	70	V
Gate to cathode voltage (open anode)	$V_{gk\text{-}kO}$	max.	5	V
Average anode current	$I_{A(AV)}$	max.	175	mA
Anode current (peak value) t_p = 10 µs; δ = 1%	I_{AM}	max.	2,5	A
Anode gate current (average)	$I_{GA(AV)}$	max.	175	mA
Anode gate current (peak value)	I_{GAM}	max.	**	
Total power dissipation at T_{amb} = 25 °C*	P_{tot}	max.	275	mW
Junction temperature	T_j	max.	150	°C
Storage temperature	T_{stg}		−65 to + 150	°C

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j\text{-}a}$	=	450	K/W

* Device mounted on a ceramic substrate of 15 mm x 15 mm x 0,5 mm.

** During switching on, the device can withstand the discharge of a capacitor of maximum value of 500 pF. This capacitor is charged when the transistor is in cut-off condition, with a collector supply voltage of 160 V and a series resistance of 100 kΩ.

▲ Provided the I_E rating is not exceeded.

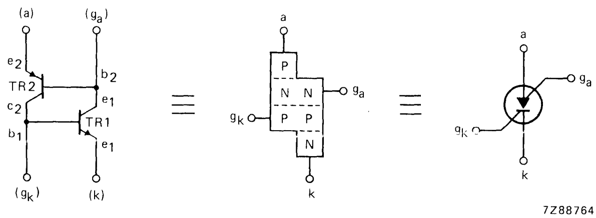


Fig. 2 Circuit diagram.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

Transistor 1 (TR1)

Collector-emitter cut-off current			
V_{CE} = 60 V; R_{BE} = 10 kΩ	I_{CER}	<	100 nA
V_{CE} = 70 V; R_{BE} = 10 kΩ; T_j = 150 °C	I_{CER}	<	10 μA
Emitter cut-off current			
V_{EB} = 5 V; I_C = 0; T_j = 150 °C	I_{EBO}	<	10 μA
Saturation voltages			
I_C = 10 mA; I_B = 1 mA	V_{CEsat}	<	0,5 V
	V_{BEsat}	<	0,9 V
D.C. current gain			
V_{CE} = 2 V; I_C = 10 mA	h_{FE}	>	50
Collector capacitance			
V_{CB} = 20 V; I_E = I_e = 0	C_c	<	5 pF
Emitter capacitance			
V_{EB} = 1 V; I_C = I_c = 0	C_e	<	25 pF
Transition frequency at f = 100 MHz			
V_{CE} = 2 V; I_C = 10 mA	f_T	=	300 MHz

Transistor 2 (TR2)

Collector-emitter cut-off current			
$-V_{CE}$ = 70 V; I_B = 0; T_j = 150 °C	$-I_{CEO}$	<	10 μA
Emitter cut-off current			
$-V_{EB}$ = 70 V; I_C = i_c = 0; T_j = 150 °C	$-I_{EBO}$	<	10 μA
D.C. current gain			
V_{CB} = 0 V; I_E = 1 mA	h_{FE}		0,25 to 2,5

THYRISTOR

Anode to cathode

On-state voltage

I_A = 50 mA; I_{ga} = 0; $R_{gk\text{-}k}$ = 10 kΩ	V_T	<	1,4 V
I_A = 1 mA; I_{ga} = 10 mA; $R_{gk\text{-}k}$ = 10 kΩ	V_T	<	1,2 V

Holding current

I_{ga} = 10 mA; $-V_{gk}$ = 2 V; $R_{gk\text{-}k}$ = 10 Ω	I_H	<	1 mA

Switching characteristics

Gate-controlled turn-on time ($t_{gt} = t_d + t_r$)
when switched from V_{gk} = −0,5 V to 4,5 V

at $R_{gk\text{-}k}$ = 1 kΩ	t_{gt}	<	0,25 μs
at $R_{gk\text{-}k}$ = 10 kΩ	t_{gt}	<	1,5 μs

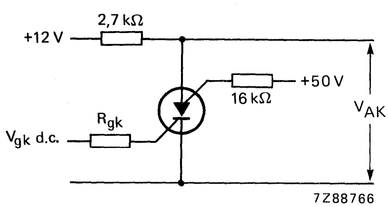


Fig. 3 Switching times test circuit.
The pulse time of V_{gk} can be adjusted in such a way that the broken line in Fig. 4 disappears, which means that the thyristor starts triggering.

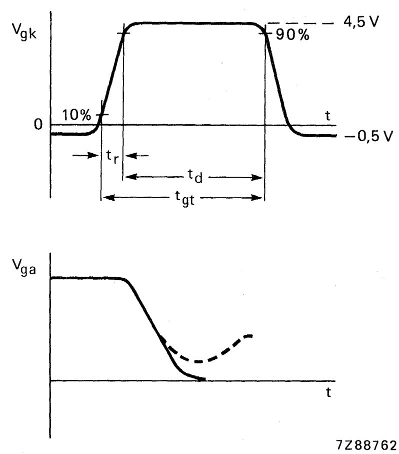


Fig. 4 Switching times waveforms.

Turn-off time (Figs 5 and 6)

R_{gk} = 1 kΩ	t_q	<	5 μs
R_{gk} = 10 kΩ	t_q	<	8 μs
R_{gk} = 10 kΩ; T_j = 125 °C	t_q	<	15 μs

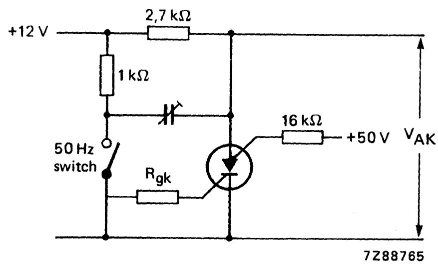


Fig. 5 Switching times test circuit.

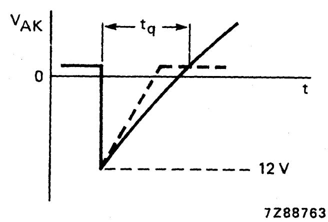


Fig. 6 Switching times waveforms.

The capacitor can be adjusted in such a way that the broken line disappears, which means that the thyristor will not trigger any more.

MOSFET N-CHANNEL DEPLETION SWITCHING TRANSISTORS

Symmetrical insulated-gate silicon MOS field-effect transistors of the N-channel depletion mode type.

The transistor is sealed in a SOT-143 envelope and features a low ON-resistance and low capacitances.

The transistor is protected against excessive input voltages by integrated back-to-back diodes between gate and substrate.

Applications:

- analog and/or digital switch
- switch driver
- convertor
- chopper

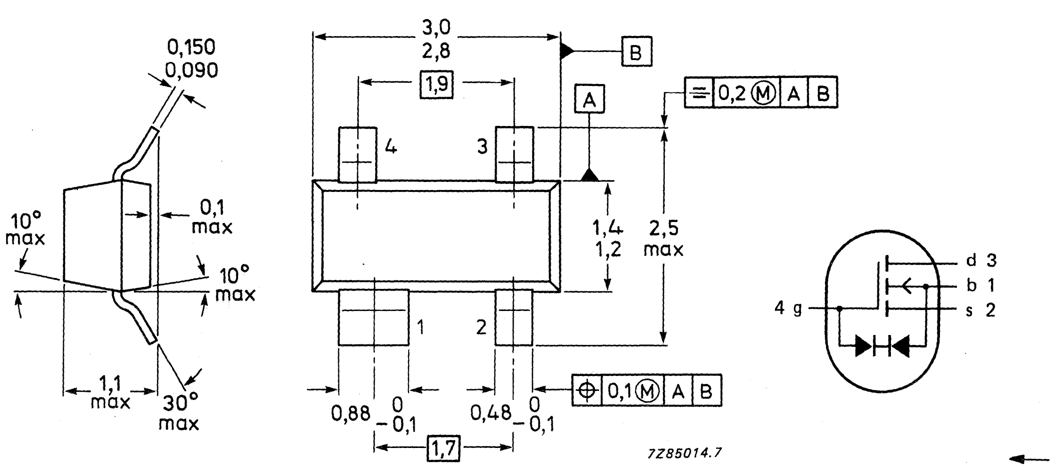
QUICK REFERENCE DATA

			BSD20	BSD22	
Drain-source voltage	V_{DS}	max.	10	20	V
Gate-source voltage	V_{GS}	max.	+10 −30	+20 −40	V V
Drain current (d.c.)	I_D	max.	50		mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	230		mW
Junction temperature	T_j	max.	125		°C
Drain-source ON-resistance V_{GS} = 10 V; V_{SB} = 0; I_D = 1 mA	R_{DSon}	<	30		Ω
Feed-back capacitance V_{GS} = V_{BS} = −5 V; V_{DS} = 10 V; f = 1 MHz	C_{rss}	typ.	0,6		pF

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-143.



TOP VIEW

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BSD20	BSD22	
Drain-source voltage	V_{DS}	max.	10	20	V
Source-drain voltage	V_{SD}	max.	10	20	V
Drain-substrate voltage	V_{DB}	max.	15	25	V
Source-substrate voltage	V_{SB}	max.	15	25	V
Gate-substrate voltage	V_{GB}	max.	±15	±25	V
Gate-source voltage	V_{GS}	max.	+15 −30	+15 −40	V V
Drain current (d.c.)	I_D	max.	50		mA
Total power dissipation up to T_{amb} = 25 °C*	P_{tot}	max.	230		mW
Storage temperature	T_{stg}		−65 to + 150		°C
Junction temperature	T_j	max.	125		°C

THERMAL RESISTANCE

From junction to ambient in free air*	$R_{th\ j\text{-}a}$	=	430	K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

			BSD20	BSD22	
Drain-source breakdown voltage $V_{GS} = V_{BS} = -5$ V; $I_S = 10$ nA	$V_{(BR)DSX}$	>	10	20	V
Source-drain breakdown voltage $V_{GD} = V_{BD} = -5$ V; $I_D = 10$ nA	$V_{(BR)SDX}$	>	10	20	V
Drain-substrate breakdown voltage $V_{GB} = 0$; $I_D = 10$ nA; open source	$V_{(BR)DBO}$	>	15	25	V
Source-substrate breakdown voltage $V_{GB} = 0$; $I_S = 10$ nA; open drain	$V_{(BR)SBO}$	>	15	25	V
Drain-source leakage current $V_{GS} = V_{BS} = -5$ V; $V_{DS} = 10$V	I_{DSoff}	typ.	1,0		nA
Source-drain leakage current $V_{GD} = V_{BD} = 5$ V; $V_{SD} = 10$V	I_{SDoff}	typ.	1,0		nA
Gate-substrate leakage current $V_{DB} = V_{SB} = 0$; $V_{GB} = \pm 15$ V	I_{GSoff}	<	10		nA

* Device mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

Forward transconductance at f = 1 kHz			
V_{DS} = 10 V; V_{SB} = 0; I_D = 20 mA	g_{fs}	>	10 mS
		typ.	15 mS
Gate-source cut-off voltage			
V_{DS} = 10 V; V_{SB} = 0; I			
I_S = 10 μA	$-V_{(P)GS}$	<	2,0 V
Drain-source ON-resistance			
I_D = 1 mA; V_{SB} = 0;			
V_{GS} = 5 V	r_{DSon}	typ.	25 Ω
		<	50 Ω
V_{GS} = 10 V	r_{DSon}	typ.	15 Ω
		<	30 Ω
Capacitances at f = 1 MHz			
V_{GS} = V_{BS} = −5V; V_{DS} = 10 V			
Feed-back capacitance	C_{rss}	typ.	0,6 pF
Input capacitance	C_{iss}	typ.	1,5 pF
Output capacitance	C_{oss}	typ.	1,0 pF
Switching times (see Fig. 2)			
V_{DD} = 10 V; V_i = −5 V to 0 V	t_{on}	typ.	1,0 ns
	t_{off}	typ.	5,0 ns

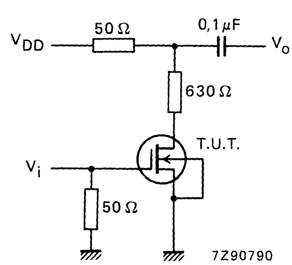


Fig. 2 Switching times test circuit.

SILICON LOW-POWER SWITCHING TRANSISTORS

P-N-P silicon transistor in a microminiature plastic envelope. It is intended for high-speed, saturated switching applications for industrial service in thick and thin-film circuits.

QUICK REFERENCE DATA

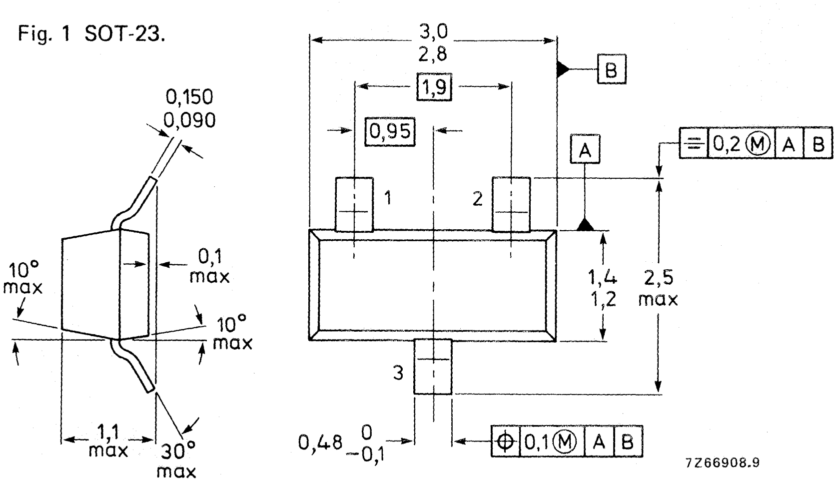
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	15	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	15	V
Collector current (peak value)	$-I_{CM}$	max.	200	mA
Total power dissipation up to T_{amb} = 65 °C	P_{tot}	max.	250	mW
Junction temperature	T_j	max.	175	°C
D.C. current gain				
$-I_C$ = 10 mA; $-V_{CE}$ = 1 V	h_{FE}	>	30	
$-I_C$ = 50 mA; $-V_{CE}$ = 1 V	h_{FE}		30 to 120	
Transition frequency at f = 500 MHz				
$-I_C$ = 50 mA; $-V_{CE}$ = 10 V	f_T	>	1,5	GHz
Turn-off time				
$-I_{Con}$ = 30 mA; $-I_{Bon}$ = $+I_{Boff}$ = 3,0 mA	t_{off}	<	30	ns

MECHANICAL DATA

Dimensions in mm

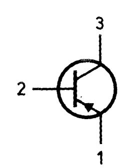
Marking code

Fig. 1 SOT-23.

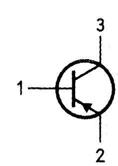


TOP VIEW

BSR12 = B5



BSR12R = B8



R-types are available on request

See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter) See Fig. 3	$-V_{CBO}$	max.	15	V
Collector-emitter voltage (open base) See Fig. 3	$-V_{CEO}$	max.	15	V
Emitter-base voltage (open collector) See Fig. 3	$-V_{EBO}$	max.	3	V
Collector current (d.c.)	$-I_C$	max.	100	mA
Collector current (peak value)	$-I_{CM}$	max.	200	mA
Total power dissipation up to T_{amb} = 65 °C**	P_{tot}	max.	250	mW
Storage temperature	T_{stg}	−65 to + 175		°C
Junction temperature	T_j	max.	175	°C

THERMAL CHARACTERISTICS*

$T_j = P x (R_{th\,j\text{-}t} + R_{th\,t\text{-}s} + R_{th\,s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\,j\text{-}t}$	=	60	K/W
From tab to soldering points	$R_{th\,t\text{-}s}$	=	280	K/W
From soldering points to ambient**	$R_{th\,s\text{-}a}$	=	90	K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Collector cut-off current				
$I_E = 0; -V_{CB} = 10$ V	$-I_{CBO}$	<	50	nA
$I_E = 0; -V_{CB} = 10$ V; $T_{amb} = 125$ °C	$-I_{CBO}$	<	5	μA
$V_{BE} = 0; -V_{CE} = 10$ V	$-I_{CES}$	<	50	nA
Breakdown voltages				
$I_E = 0; -I_C = 10$ μA	$-V_{(BR)CBO}$	>	15	V
$V_{BE} = 0; -I_C = 10$ μA	$-V_{(BR)CES}$	>	15	V
$I_C = 0; -I_E = 100$ μA	$-V_{(BR)EBO}$	>	3	V
Collector-emitter sustaining voltage				
$I_B = 0; -I_C = 10$ mA	$-V_{CEOsust}$	>	15	V
Saturation voltages▲				
$-I_C = 10$ mA; $-I_B = 1$ mA	$-V_{CEsat}$	<	130	mV
	$-V_{BEsat}$		725 to 920	mV
$-I_C = 50$ mA; $-I_B = 5$ mA	$-V_{CEsat}$	typ.	180	mV
		<	270	mV
	$-V_{BEsat}$		800 to 1150	mV
$-I_C = 100$ mA; $-I_B = 10$ mA	$-V_{CEsat}$	<	450	mV
	$-V_{BEsat}$		900 to 1500	mV

▲ Measured under pulse conditions; $t_p = 300$ μs; $\delta = 0{,}01$.
* See *Thermal characteristics.*
** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

D.C. current gain *

$-I_C$ = 1 mA; $-V_{CE}$ = 1 V	h_{FE}	>	30
$-I_C$ = 10 mA; $-V_{CE}$ = 1 V	h_{FE}	>	30
$-I_C$ = 50 mA; $-V_{CE}$ = 1 V	h_{FE}		30 to 120
$-I_C$ = 50 mA; $-V_{CE}$ = 1 V; T_{amb} = 55 °C	h_{FE}	>	30
$-I_C$ = 100 mA; $-V_{CE}$ = 1 V	h_{FE}	>	20

Transition frequency at f = 500 MHz

$-I_C$ = 50 mA; $-V_{CE}$ = 10 V	f_T	>	1,5 GHz

Collector capacitance

$I_E = I_e = 0$; $-V_{CB}$ = 5 V	C_c	<	4,5 pF

Emitter capacitance

$I_C = I_c = 0$; $-V_{EB}$ = 0,5 V	C_e	<	6,0 pF

Switching times

Turn-on time	t_{on}	<	20 ns
Turn-off time	t_{off}	<	30 ns

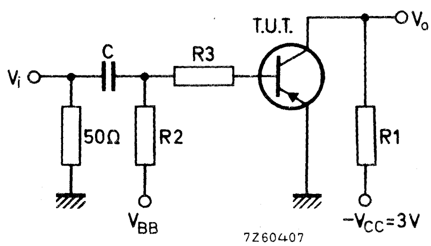


Fig. 2 Test circuit switching times.

Pulse generator

Pulse duration	t_p	= 400 ns
Rise time	t_r	< 1 ns
Output impedance	Z_o	= 50 Ω

Sampling scope

Rise time	t_r	< 1 ns
Input impedance	Z_i	= 100 kΩ

	V_i V	V_{BB} V	R1 Ω	R2 kΩ	R3 kΩ	$-I_{Con}$ mA	$-I_{Bon}$ mA	I_{Boff} mA	C μF
t_{on}	−6,85	0	94	1,0	2,0	30	3,0	—	0,1
t_{off}	11,7	−9,85	94	1,0	2,0	30	3,0	3,0	0,1

* Measured under pulse conditions; t_p = 300 μs; δ = 0,01.

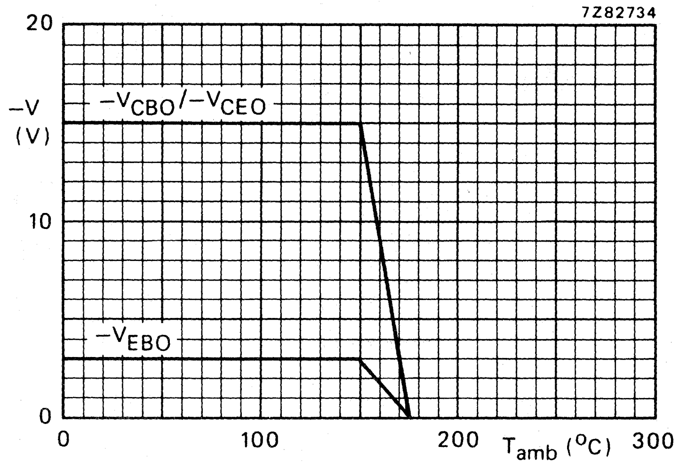


Fig. 3 Voltage derating curves.

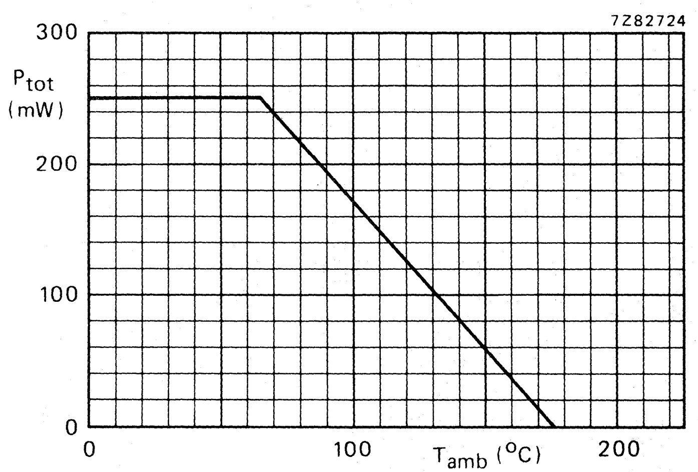


Fig. 4 Power derating curve.

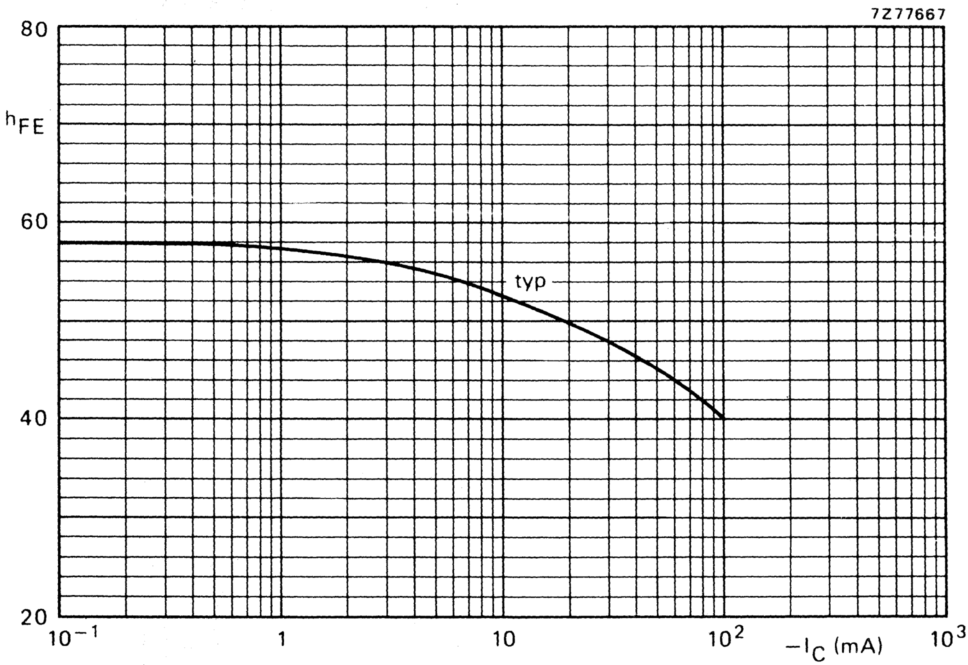


Fig. 5 $-V_{CE}$ = 1 V; T_{amb} = 25 °C.

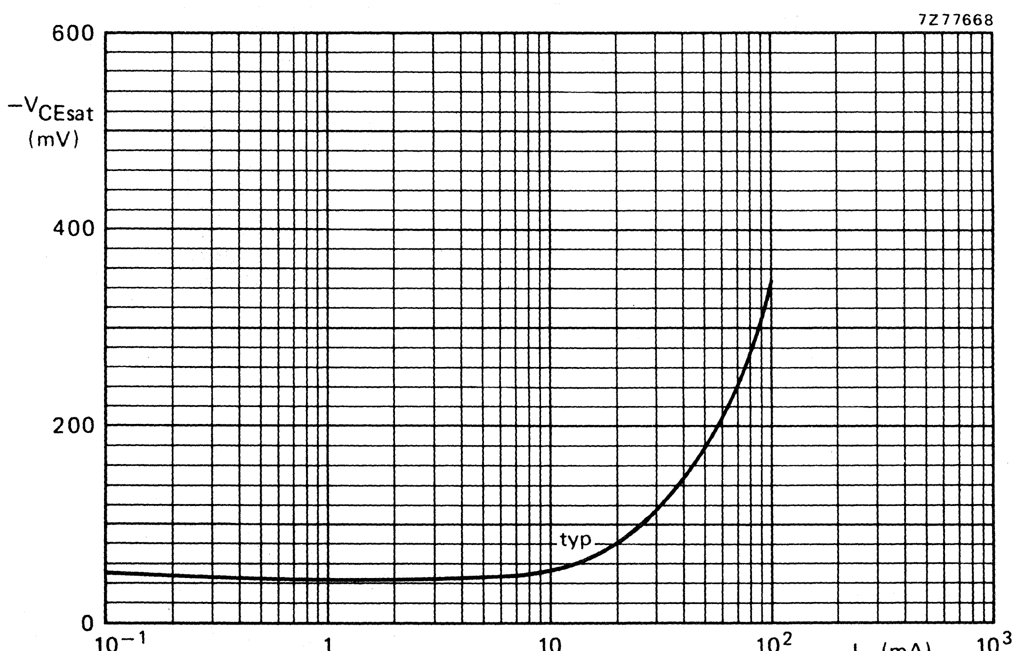


Fig. 6 V_{CEsat} as a function of I_C at I_C/I_B = 10.

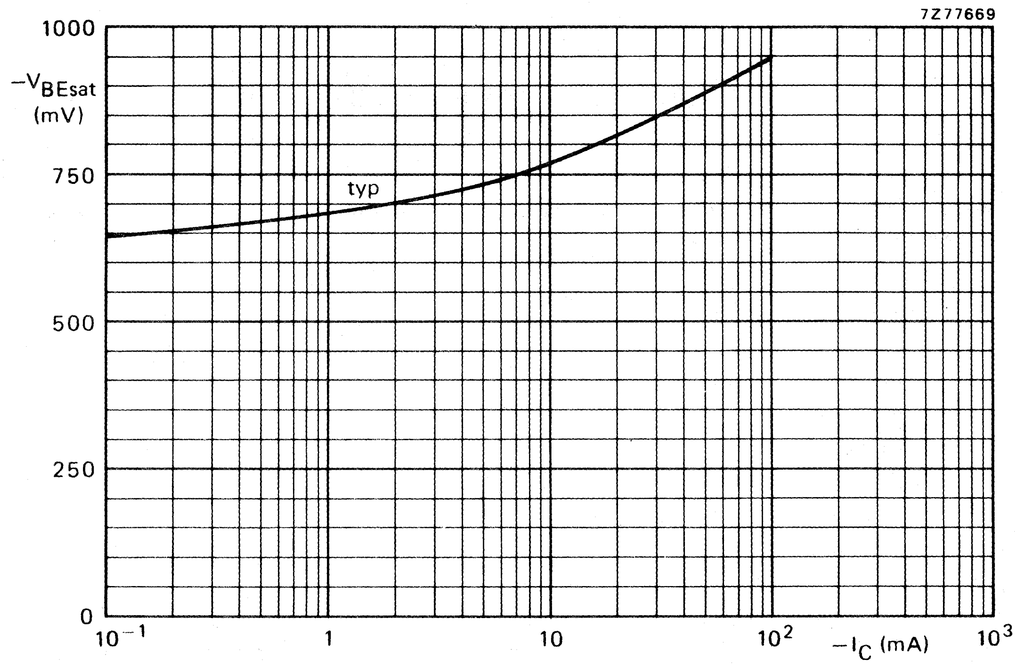


Fig. 7 V_{BEsat} as a function of I_C at $I_C/I_B = 10$.

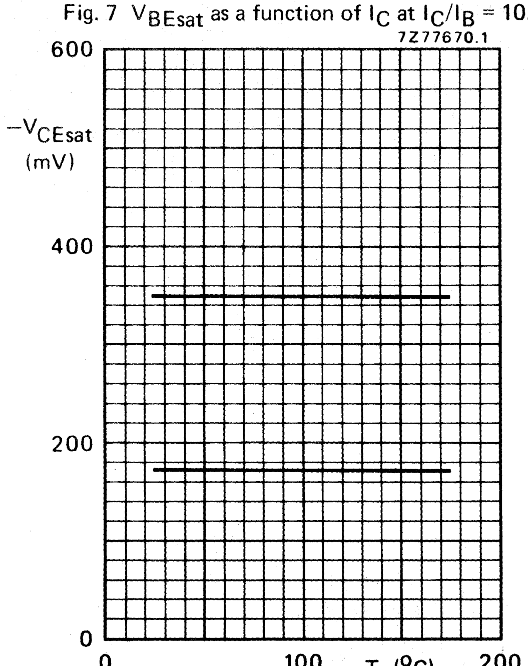


Fig. 8 V_{CEsat} as a function of T_j; typical values.
Upper graph at I_C = 100 mA; I_B = 10 mA. Lower graph at I_C = 50 mA and I_B = 5 mA.

SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N silicon transistors, in a microminiature plastic envelope intended for switching and linear applications in thick and thin-film circuits.

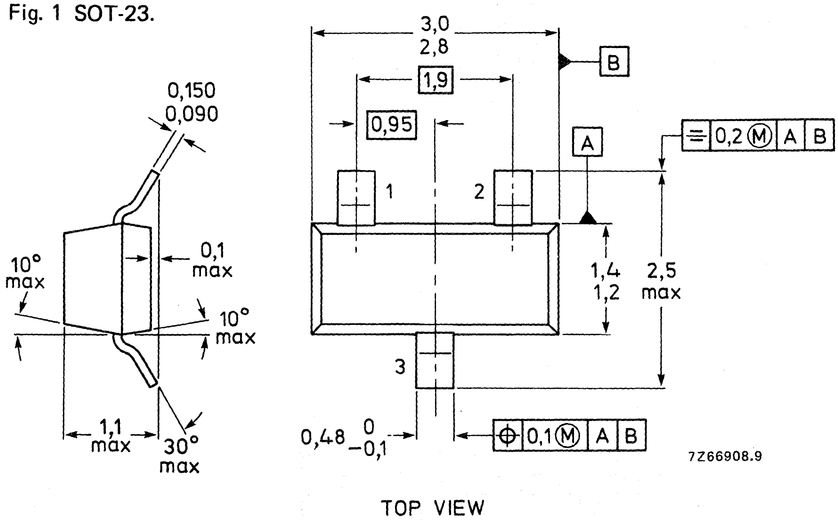
QUICK REFERENCE DATA

			BSR13	BSR14	
Collector-base voltage (open emitter)	V_{CBO}	max.	60	75	V
Collector-emitter voltage (open base)	V_{CEO}	max.	30	40	V
Emitter-base voltage (open collector)	V_{EBO}	max.	5	6	V
Collector current (d.c.)	I_C	max.	800		mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	425		mW
Junction temperature	T_j	max.	175		°C
D.C. current gain					
I_C = 150 mA; V_{CE} = 10 V	h_{FE}		100 to 300		
I_C = 500 mA; V_{CE} = 10 V	h_{FE}	>	30	40	
Transition frequency at f = 100 MHz					
I_C = 20 mA; V_{CE} = 20 V	f_T	>	250	300	MHz

MECHANICAL DATA

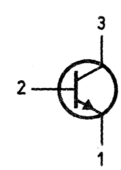
Dimensions in mm

Fig. 1 SOT-23.

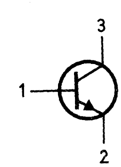


Marking code

BSR13 = U7
BSR14 = U8



BSR13R = U71
BSR14R = U81



R-types are available on request.

See also Soldering recommendations.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BSR13	BSR14	
Collector-base voltage (open emitter) see Fig. 4	V_{CBO}	max.	60	75	V
Collector-emitter voltage (open base) see Fig. 4	V_{CEO}	max.	30	40	V
Emitter-base voltage (open collector) see Fig. 4	V_{EBO}	max.	5	6	V
Collector current (d.c.)	I_C	max.	800		mA
Total power dissipation** up to T_{amb} = 25 °C	P_{tot}	max.	425		mW
Storage temperature	T_{stg}		−65 to + 175		°C
Junction temperature	T_j	max.	175		°C

THERMAL CHARACTERISTICS*

$T_j = P \times (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	30	K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	260	K/W
From soldering points to ambient**	$R_{th\ s\text{-}a}$	=	60	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BSR13	BSR14	
Collector cut-off current					
$I_E = 0$; V_{CB} = 50 V	I_{CBO}	<	30	–	nA
$I_E = 0$; V_{CB} = 60 V	I_{CBO}	<	–	10	nA
$I_E = 0$; V_{CB} = 50 V; T_j = 150 °C	I_{CBO}	<	10	–	µA
$I_E = 0$; V_{CB} = 60 V; T_j = 150 °C	I_{CBO}	<	–	10	µA
V_{EB} = 3 V; V_{CE} = 60 V	I_{CEX}	<	–	10	nA
Base current with reverse biased emitter junction V_{EB} = 3 V; V_{CE} = 60 V	I_{BEX}	<	–	20	nA
Emitter cut-off current $I_C = 0$; V_{EB} = 3 V	I_{EBO}	<	30	15	nA
Saturation voltages ▲					
I_C = 150 mA; I_B = 15 mA	V_{CEsat}	<	400	300	mV
	V_{BEsat}	<	1300	–	mV
	V_{BEsat}		–	0,6 to 1,2	V
I_C = 500 mA; I_B = 50 mA	V_{CEsat}	<	1600	1000	mV
	V_{BEsat}	<	2600	2000	mV

* See *Thermal characteristics.*

** Device mounted on a ceramic substrate of 15 mm x 15 mm x 0,7 mm.

▲ Measured under pulsed conditions to avoid excessive dissipation $t_p \leq 300\ \mu s$; $\delta \leq 0{,}02$.

D.C. current gain *			
I_C = 0,1 mA; V_{CE} = 10 V	h_{FE}	> 35	
I_C = 1 mA; V_{CE} = 10 V	h_{FE}	> 50	
I_C = 10 mA; V_{CE} = 10 V	h_{FE}	> 75	
I_C = 150 mA; V_{CE} = 10 V	h_{FE}	100 to 300	
I_C = 150 mA; V_{CE} = 1 V	h_{FE}	> 50	
I_C = 500 mA; V_{CE} = 10 V BSR13; R	h_{FE}	> 30	
I_C = 500 mA; V_{CE} = 10 V BSR14; R	h_{FE}	> 40	
Transition frequency at f = 100 MHz			
I_C = 20 mA; V_{CE} = 20 V BSR13; R	f_T	> 250	MHz
I_C = 20 mA; V_{CE} = 20 V BSR14; R	f_T	> 300	MHz
Collector capacitance at f = 1 MHz			
$I_E = I_e = 0$; V_{CB} = 10 V	C_c	< 8	pF
h parameters (common emitter) at f = 1 kHz			
I_C = 1 mA; V_{CE} = 10 V		BSR14	
input impedance	h_{ie}	2 to 8	kΩ
reverse voltage transfer ratio	h_{re}	< 8.10^{-4}	
small signal current gain	h_{fe}	50 to 300	
output admittance	h_{oe}	5 to 35	μS
I_C = 10 mA; V_{CE} = 10 V			
input impedance	h_{ie}	0,25 to 1,25	kΩ
reverse voltage transfer ratio	h_{re}	< 4.10^{-4}	
small signal current gain	h_{fe}	75 to 375	
output admittance	h_{oe}	25 to 200	μS

* Measured under pulsed conditions to avoid excessive dissipation; pulse duration $t_p \leqslant 300\ \mu s$; duty factor $\delta \leqslant 0{,}02$.

Switching times (between 10% and 90% levels)

		BSR14		
Turn-on time switched to I_C = 150 mA (see Fig. 2)				
delay time	t_d	<	10	ns
rise time	t_r	<	25	ns
Turn-off time switched from I_C = 150 mA (see Fig. 3)				
storage time	t_s	<	225	ns
fall time	t_f	<	60	ns

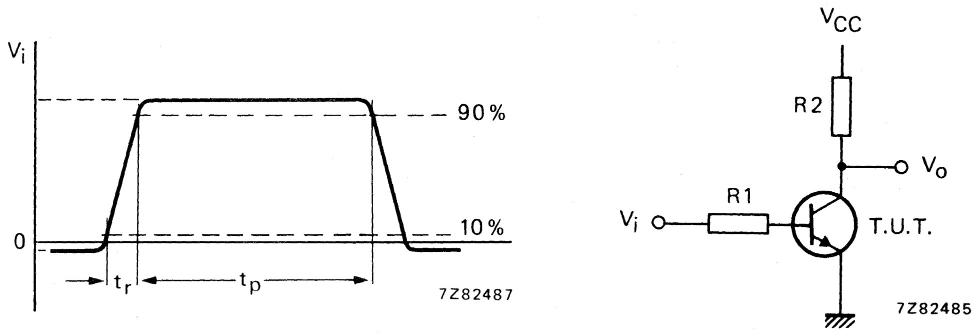


Fig. 2 Waveform and test circuit delay and rise time.

V_i = –0,5 to + 9,9 V; V_{CC} = 30 V; R1 = 619 Ω; R2 = 200 Ω.

Pulse generator:			
pulse duration	t_p	⩽	200 ns
rise time	t_r	⩽	2 ns
duty factor	δ	=	2 %

Oscilloscope:			
input impedance	Z_i	>	100 kΩ
input capacitance	C_i	<	12 pF
rise time	t_r	<	5 ns

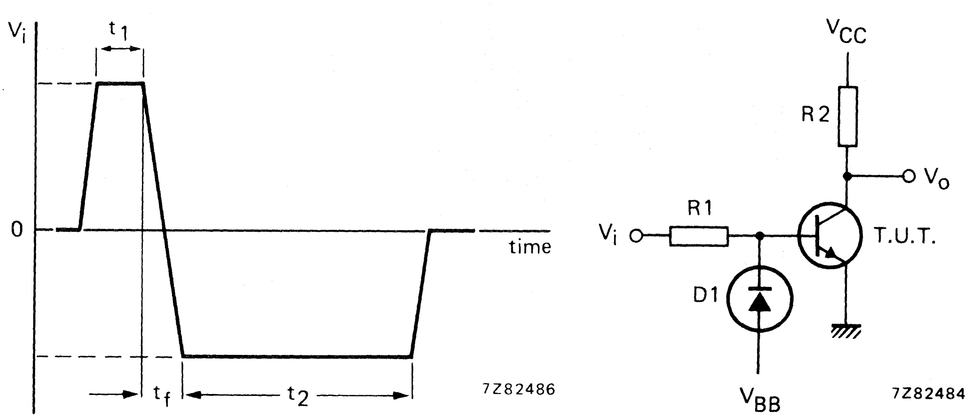


Fig. 3 Waveform and test circuit storage and fall time.

V_i = –13,8 to + 16,2 V; V_{CC} = 30 V; $-V_{BB}$ = 3 V; R1 = 1 kΩ; R2 = 200 Ω.

Pulse generator:			
fall time	t_f	<	5 ns
pulse time	t_1	=	100 μs
	t_2	=	500 μs

Oscilloscope:			
input impedance	Z_i	>	100 kΩ
input capacitance	C_i	<	12 pF
rise time	t_r	<	5 ns

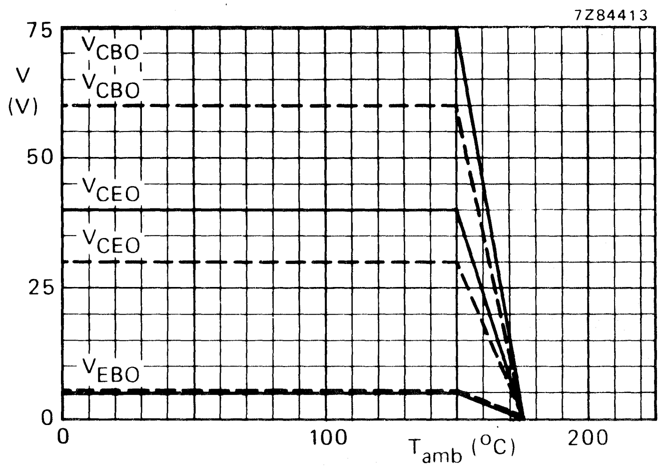


Fig. 4 Voltage derating curve.
– – – BSR13 ——— BSR14.

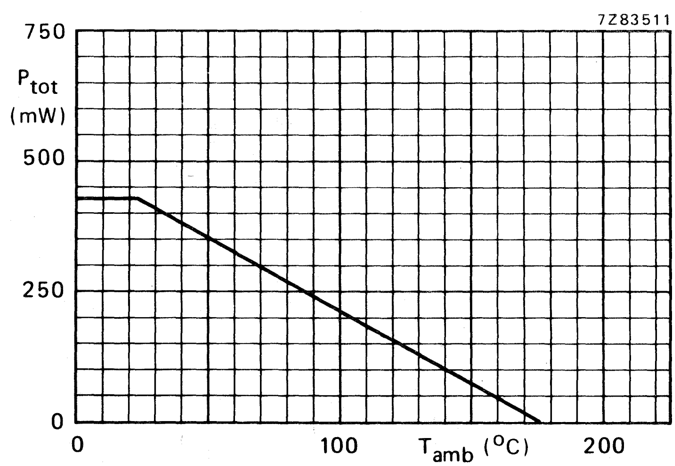


Fig. 5 Power derating curve.

SILICON PLANAR EPITAXIAL TRANSISTORS

P-N-P silicon transistors, in a microminiature plastic envelope, intended for medium power switching and general purpose amplifier applications in thick and thin-film circuits.

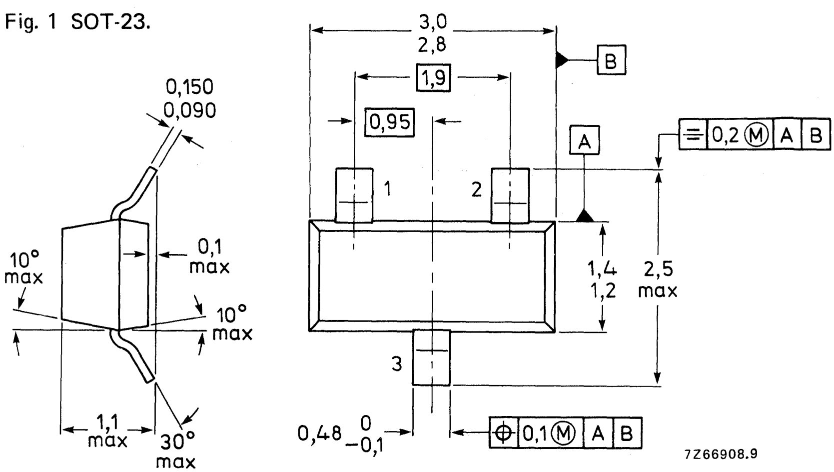
QUICK REFERENCE DATA

			BSR15	BSR16	
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	60	60	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	40	60	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5		V
Collector current (d.c.)	$-I_C$	max.	600		mA
Total power dissipation up to T_{amb} = 25 ^oC	P_{tot}	max.	425		mW
Junction temperature	T_j	max.	175		^oC
D.C. current gain $-I_C$ = 500 mA; $-V_{CE}$ = 10 V	h_{FE}	>	30	50	
Turn-off switching time $-I_{Con}$ = 150 mA; $-I_{Bon}$ = I_{Boff} = 15 mA	t_{off}	>	100		ns
Transition frequency at f = 100 MHz $-I_C$ = 50 mA; $-V_{CE}$ = 20 V	f_T	>	200		MHz

MECHANICAL DATA

Dimensions in mm

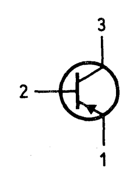
Fig. 1 SOT-23.



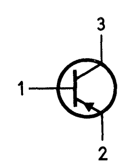
TOP VIEW

Marking code

BSR15 = T7
BSR16 = T8



BSR15R = T71
BSR16R = T81



R-types are available on request.

See also Soldering recommendations.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BSR15	BSR16	
Collector-base voltage (open emitter) See Figs 5 and 6	$-V_{CBO}$	max.	60	60	V
Collector-emitter voltage (open base) See Figs 5 and 6	$-V_{CEO}$	max.	40	60	V
Emitter-base voltage (open collector) See Figs 5 and 6	$-V_{EBO}$	max.	5	5	V
Collector current (d.c.)	$-I_C$	max.	600		mA
Power dissipation up to T_{amb} = 25 °C**	P_{tot}	max.	425		mW
Storage temperature	T_{stg}		−65 to + 175		°C
Junction temperature	T_j	max.	175		°C

THERMAL CHARACTERISTICS*

$T_j = P \times (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	30	K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	260	K/W
From soldering points to ambient**	$R_{th\ s\text{-}a}$	=	60	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BSR15	BSR16	
Collector cut-off current					
$I_E = 0$; $-V_{CB}$ = 50 V	$-I_{CBO}$	<	20	10	nA
$I_E = 0$; $-V_{CB}$ = 50 V; T_j = 150 °C	$-I_{CBO}$	<	20	10	μA
$-V_{EB}$ = 0,5 V; $-V_{CE}$ = 30 V	$-I_{CEX}$	<	50		nA
Base current with reverse biased emitter junction					
$-V_{EB}$ = 3 V; $-V_{CE}$ = 30 V	$-I_{BEX}$	<	50		nA
Saturation voltages ▲					
$-I_C$ = 150 mA; $-I_B$ = 15 mA	$-V_{CEsat}$	<	0,4		V
	$-V_{BEsat}$	<	1,3		V
$-I_C$ = 500 mA; $-I_B$ = 50 mA	$-V_{CEsat}$	<	1,6		V
	$-V_{BEsat}$	<	2,6		V

* See *Thermal characteristics.*
** Device mounted on a ceramic substrate of 15 mm x 15 mm x 0,7 mm.
▲ Measured under pulsed conditions to avoid excessive dissipation pulse duration $t_p \leq 300\ \mu s$; duty factor $\delta \leq 0{,}02$.

			BSR15	BSR16	
D.C. current gain *					
$-I_C$ = 0,1 mA; $-V_{CE}$ = 10 V	h_{FE}	>	35	75	
$-I_C$ = 1 mA; $-V_{CE}$ = 10 V	h_{FE}	>	50	100	
$-I_C$ = 10 mA; $-V_{CE}$ = 10 V	h_{FE}	>	75	100	
$-I_C$ = 150 mA; $-V_{CE}$ = 10 V	h_{FE}		100 to 300		
$-I_C$ = 500 mA; $-V_{CE}$ = 10 V	h_{FE}	>	30	50	
Transition frequency at f = 100 MHz					
$-I_C$ = 50 mA; $-V_{CE}$ = 20 V; T_{amb} = 25 °C	f_T	>	200		MHz
Collector capacitance at f = 1 MHz					
$I_E = I_e = 0$; $-V_{CB}$ = 10 V	C_c	<	8		pF
Emitter capacitance at f = 1 MHz					
$I_C = I_c = 0$; $-V_{EB}$ = 2 V	C_e	<	30		pF
Switching times (between 10% and 90% levels)					
Turn-on time when switched to $-I_C$ = 150 mA; $-I_B$ = 15 mA; (see Fig. 3)					
delay time	t_d	<	10		ns
rise time	t_r	<	40		ns
turn-on time ($t_d + t_r$)	t_{on}	<	45		ns
Turn-off time when switched from $-I_C$ = 150 mA; $-I_B$ = 15 mA to cut-off with + I_{BM} = 15 mA (see Fig. 4)					
storage time	t_s	<	80		ns
fall time	t_f	<	30		ns
turn-off time ($t_s + t_f$)	t_{off}	<	100		ns

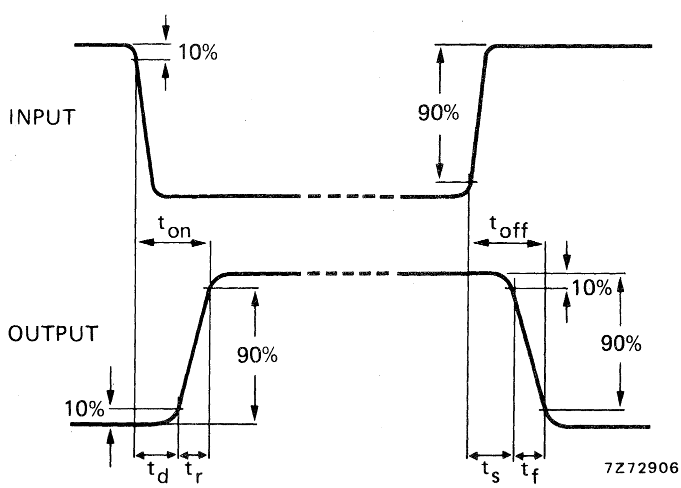


Fig. 2 Switching time waveforms.

* Measured under pulsed conditions to avoid excessive dissipation; pulse duration $t_p \leqslant 300\ \mu s$; duty factor $\delta \leqslant 0{,}02$.

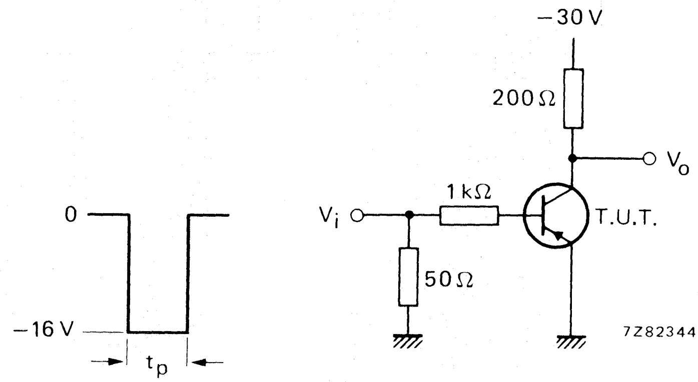


Fig. 3 Turn-on switching time test circuit.

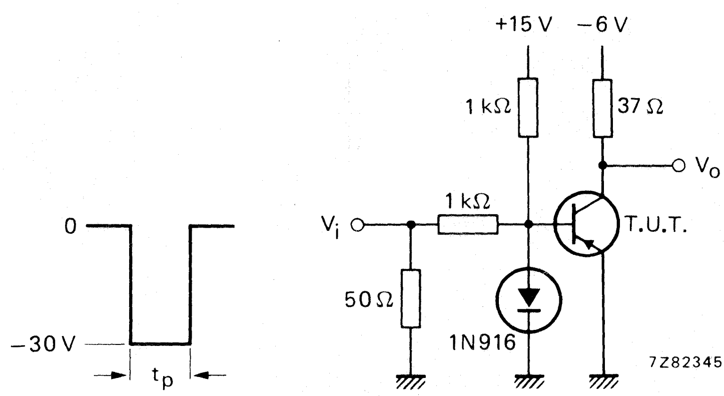


Fig. 4 Turn-off switching time test circuit.

Input pulse generator:	frequency	f	=	150	Hz
Fig. 3 and Fig. 4	pulse duration	t_p	=	200	ns
	rise time	t_r	$\leqslant$	2	ns
	output impedance	Z_o	=	50	Ω
Output oscilloscope:	rise time	t_r	$\leqslant$	5	ns
Fig. 3 and Fig. 4	input impedance	Z_i	=	10	MΩ

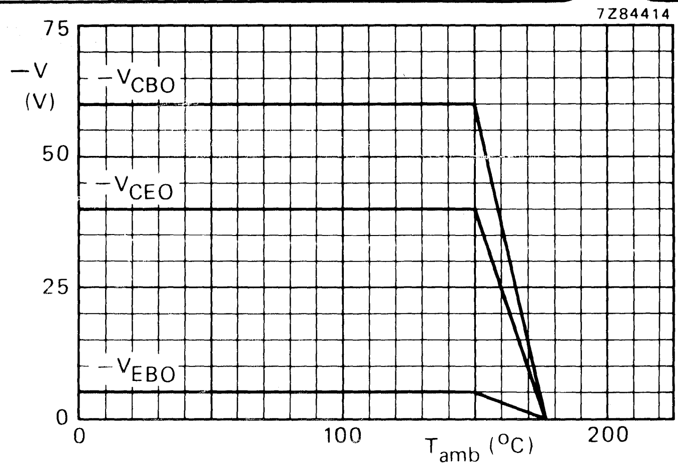


Fig. 5 Voltage derating curves BSR15.

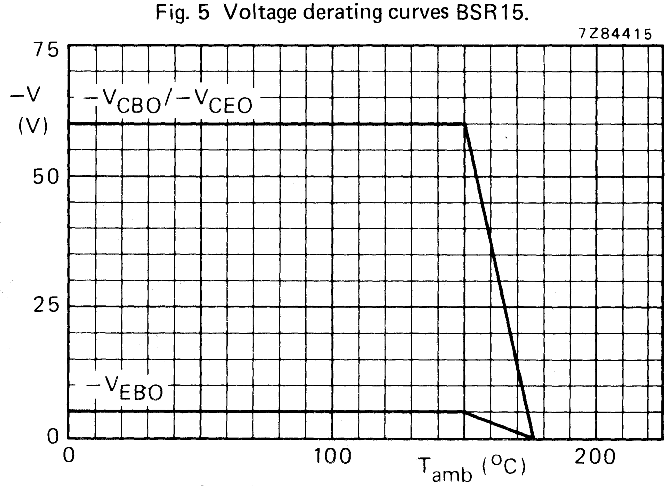


Fig. 6 Voltage derating curves BSR16.

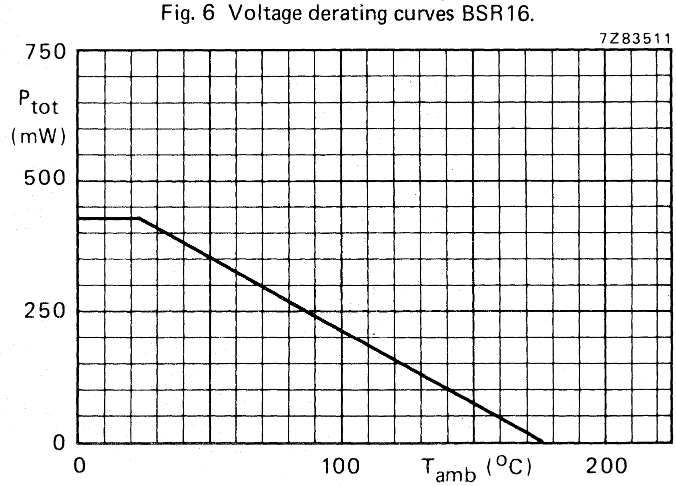


Fig. 7 Power derating curve BSR15; R/BSR16.

SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N silicon transistor in a microminiature plastic envelope intended for switching and linear applications in thick and thin-film circuits.

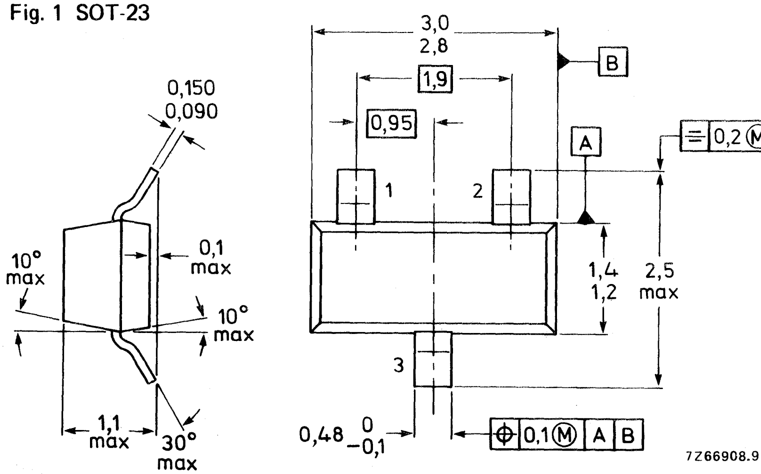
QUICK REFERENCE DATA

Collector-base voltage (open emitter)		V_{CBO}	max.	60 V
Collector-emitter voltage (open base)		V_{CEO}	max.	40 V
Emitter-base voltage (open collector)		V_{EBO}	max.	6 V
Collector current (d.c.)		I_C	max.	200 mA
Total power dissipation up to T_{amb} = 25 °C		P_{tot}	max.	350 mW
Junction temperature		T_j	max.	150 °C
D.C. current gain				
I_C = 10 mA; V_{CE} = 1 V	BSR17	h_{FE}		50 to 150
I_C = 10 mA; V_{CE} = 1 V	BSR17A	h_{FE}		100 to 300
Transition frequency at f = 500 MHz				
I_C = 10 mA; V_{CE} = 20 V	BSR17	f_T	>	250 MHz
I_C = 10 mA; V_{CE} = 20 V	BSR17A	f_T	>	300 MHz

MECHANICAL DATA

Dimensions in mm

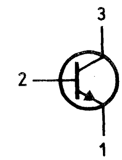
Fig. 1 SOT-23



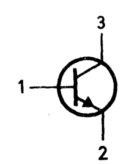
TOP VIEW

Marking code

BSR17 = U9
BSR17A = U92



BSR17R = U91
BSR17AR = U93



R-types are available on request.
See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	V_{CBO}	max.	60	V
Collector-emitter voltage (open base)	V_{CEO}	max.	40	V
Emitter base voltage (open collector)	V_{EBO}	max.	6	V
Collector current (d.c.)	I_C	max.	200	mA
Power dissipation up to T_{amb} = 25 °C**	P_{tot}	max.	350	mW
Storage temperature	T_{stg}	−55 to + 150		°C
Junction temperature	T_j	max.	150	°C

THERMAL CHARACTERISTICS*

$T_j = Px\ (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	50	K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280	K/W
From soldering points to ambient**	$R_{th\ s\text{-}a}$	=	90	K/W

CHARACTERISTICS

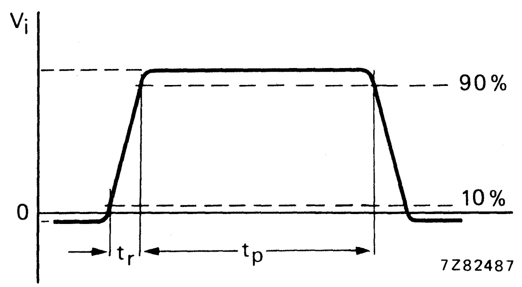
T_j = 25 °C unless otherwise specified.

Collector cut-off current				
$I_E = 0$; V_{CB} = 30 V; T_j = 150 °C	I_{CBO}	<	5	μA
V_{EB} = 3 V; V_{CE} = 30 V	I_{CEX}	<	50	nA
Base current with reverse biased emitter junction				
V_{EB} = 3 V; V_{CE} = 30 V	I_{BEX}	<	50	nA
Saturation voltages▲				
I_C = 10 mA; I_B = 1 mA	V_{CEsat}	<	200	mV
	V_{BEsat}	650 to	850	mV
I_C = 50 mA; I_B = 5 mA	V_{CEsat}	<	300	mV
	V_{BEsat}	<	950	mV
Collector capacitance at f = 1 MHz				
$I_E = I_e = 0$; V_{CB} = 5 V	C_c	<	4	pF
Emitter capacitance at f = 1 MHz				
$I_C = I_c = 0$; V_{EB} = 0,5 V	C_e	<	8	pF

▲ Measured under pulsed conditions; pulse duration $t_p \leqslant 300\ \mu s$; duty factor $\delta \leqslant 0{,}02$.
* See *Thermal characteristics.*
** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

			BSR17	BSR17A	
D.C. current gain*					
$I_C = 0,1$ mA; $V_{CE} = 1$ V	h_{FE}	>	20	40	
$I_C = 1$ mA; $V_{CE} = 1$ V	h_{FE}	>	35	70	
$I_C = 10$ mA; $V_{CE} = 1$ V	h_{FE}	>	50	100	
		<	150	300	
$I_C = 50$ mA; $V_{CE} = 1$ V	h_{FE}	>	30	60	
$I_C = 100$ mA; $V_{CE} = 1$ V	h_{FE}	>	15	30	
Transition frequency at f = 100 MHz					
$I_C = 10$ mA; $V_{CE} = 20$ V	f_T	>	250	300	MHz
h-parameters (common emitter)					
$I_C = 1$ mA; $V_{CE} = 10$ V; f = 1 kHz					
Input impedance	h_{ie}		1 to 8	1 to 10	kΩ
Reverse voltage transfer ratio	h_{re}		0,1 to 5	0,5 to 8	10^{-4}
Small-signal current gain	h_{fe}		50 to 200	100 to 400	
Output admittance	h_{oe}		1 to 40	1 to 40	μS

Switching times (between 10% and 90% levels)				
Turn on time switched to				
$I_C = 10$ mA; $I_B = 1$ mA; $V_{EB} = 0,5$ V				
delay time	t_d	<	35	ns
rise time	t_r	<	35	ns



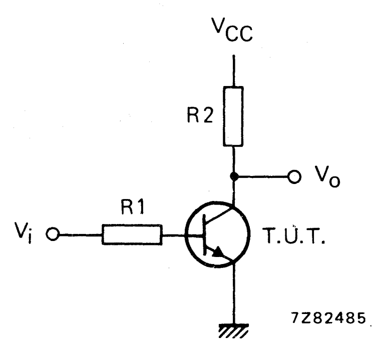
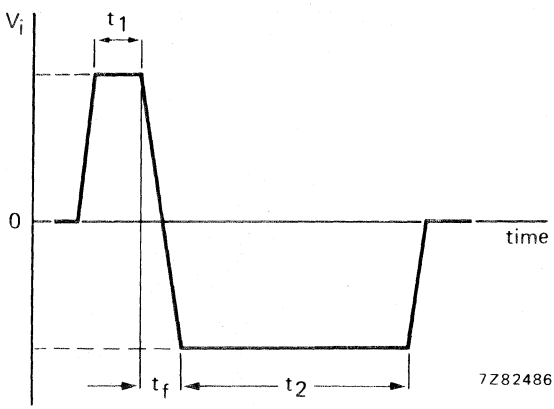


Fig. 2 Delay and rise time equivalent circuit.
$V_i = -0,5$ to $+10,6$ V; $V_{CC} = 3$ V; R1 = 10 kΩ; R2 = 275 Ω;
total shunt capacitance of test jig and connectors = $C_s \leqslant 4$ pF.
Pulse generator: pulse duration 300 ns; fall time < 1 ns; duty factor 2%.

		BSR17	BSR17A
Turn off time switched from $I_C = 10$ mA; $I_{Bon} = -I_{Boff} = 1$ mA			
storage time	t_s	< 175	200 ns
fall time	t_f	< 50	50 ns



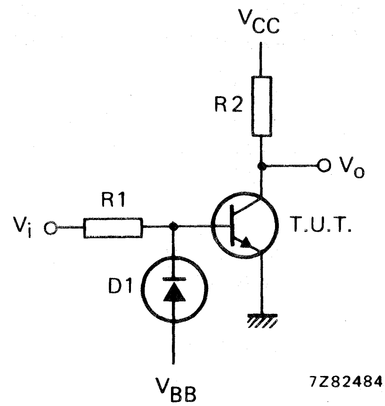


Fig. 3 Storage and fall time equivalent test circuit.

$V_i = -9{,}1$ to $+10{,}9$ V; $V_{CC} = 3$ V; $V_{BB} = 0$ V (ground); R1 = 10 kΩ; R2 = 275 Ω; total shunt capacitance of test jig and connectors = $C_s \leqslant 4$ pF.
Pulse generator: pulse duration $t_1 = 10$ to 500 μs; fall time $t_f < 1$ ns; duty factor $\delta = 2\%$.

SILICON LOW-POWER SWITCHING TRANSISTORS

P-N-P silicon transistor in a microminiature plastic envelope, intended for switching and linear applications in thick and thin-film circuits.

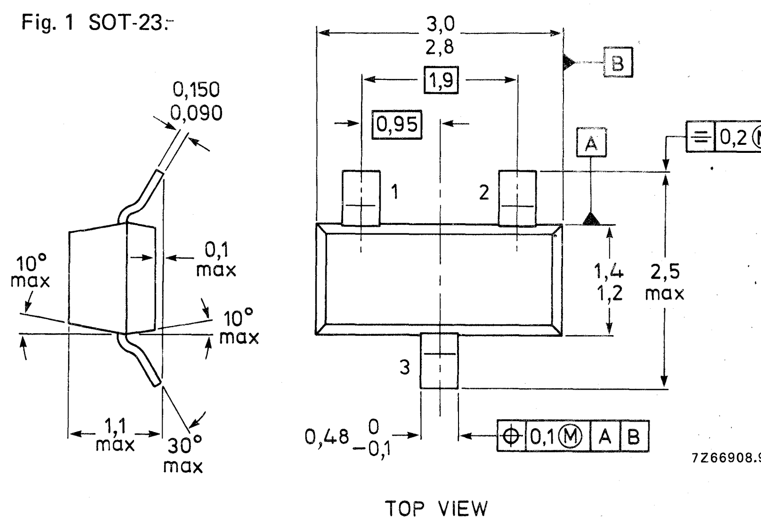
QUICK REFERENCE DATA

Collector-base voltage (open emitter)		$-V_{CBO}$	max.	40 V
Collector-emitter voltage (open base)		$-V_{CEO}$	max.	40 V
Collector current (d.c.)		$-I_C$	max.	200 mA
Total power dissipation up to T_{amb} = 65 °C		P_{tot}	max.	250 mW
Junction temperature		T_j	max.	150 °C
D.C. current gain				
$-I_C$ = 10 mA; $-V_{CE}$ = 1 V	BSR18	h_{FE}		50 to 150
$-I_C$ = 10 mA; $-V_{CE}$ = 1 V	BSR18A	h_{FE}		100 to 300
Transition frequency at f = 500 MHz				
$-I_C$ = 10 mA; $-V_{CE}$ = 20 V	BSR18	f_T	>	200 MHz
$-I_C$ = 10 mA; $-V_{CE}$ = 20 V	BSR18A	f_T	>	250 MHz

MECHANICAL DATA

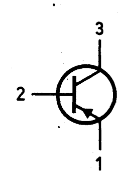
Dimensions in mm

Fig. 1 SOT-23.

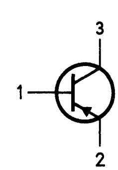


Marking code

BSR18 = T9
BSR18A = T92



BSR18R = T91
BSR18AR = T93



R-types are available on request.
See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	40 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	40 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5 V
Collector current (d.c.)	$-I_C$	max.	200 mA
Total power dissipation up to $T_{amb} \leqslant 65\ ^oC$	P_{tot}	max.	200 mW
Storage temperature	T_{stg}	−55 to +150	^oC
Junction temperature	T_j	max.	150 ^oC

THERMAL CHARACTERISTICS*

$T_j = P x (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	50 K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280 K/W
From soldering points to ambient**	$R_{th\ s\text{-}a}$	=	90 K/W

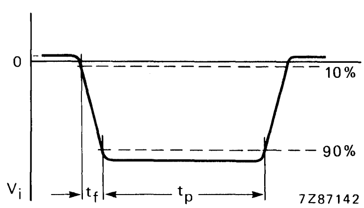
CHARACTERISTICS

$T_{amb} = 25\ ^oC$ unless otherwise specified

Collector cut-off current			
$I_E = 0; -V_{CB} = 30$ V	$-I_{CBO}$	<	50 nA
Emitter cut-off current			
$I_C = 0; -V_{EB} = 3$ V	$-I_{EBO}$	<	50 nA
Saturation voltages ▲			
$-I_C = 10$ mA; $-I_B = 1$ mA	$-V_{CEsat}$	<	250 mV
	$-V_{BEsat}$		650 to 850 mV
$-I_C = 50$ mA; $-I_B = 5$ mA	$-V_{CEsat}$	<	400 mV
	$-V_{BEsat}$	<	950 mV
Collector capacitance at f = 100 kHz			
$I_E = I_e = 0; -V_{CB} = 5$ V	C_c	<	4,5 pF
Emitter capacitance at f = 100 kHz			
$I_C = I_c = 0; -V_{EB} = 0,5$ V	C_e	<	10 pF

* See *Thermal characteristics.*
** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.
▲ Measured under pulse conditions; $t_p = 300\ \mu s$; $\delta = 0,01$.

			BSR18	BSR18A
D.C. current gain*				
$-I_C$ = 0,1 mA; $-V_{CE}$ = 1 V	h_{FE}	>	30	60
$-I_C$ = 1,0 mA; $-V_{CE}$ = 1 V	h_{FE}	>	40	80
$-I_C$ = 10 mA; $-V_{CE}$ = 1 V	h_{FE}		50 to 150	100 to 300
$-I_C$ = 50 mA; $-V_{CE}$ = 1 V	h_{FE}	>	30	60
$-I_C$ =100 mA; $-V_{CE}$ = 1 V	h_{FE}	>	15	30
Transition frequency at f = 100 MHz				
$-I_C$ = 10 mA; $-V_{CE}$ = 20 V	f_T	>	200	250 MHz
Noise figure at R_S = 1 kΩ				
$-I_C$ = 100 μA; $-V_{CE}$ = 5 V				
f = 10 to 15 700 Hz	F	<	5	4 dB
h parameters (common emitter) at f = 1 kHz				
$-I_C$ = 1 mA; $-V_{CE}$ = 10 V				
input impedance	h_{ie}		0,5 to 8	2 to 12 kΩ
reverse voltage transfer ratio	h_{re}		0,1 to 5.10^{-4}	1 to 10.10^{-4}
small signal current gain	h_{fe}		50 to 200	100 to 400
output admittance	h_{oe}		1 to 40	3 to 60 μS
Switching times (between 10% and 90% levels)				
$-I_C$ = 10 mA; $-I_{Bon}$ = $+I_{Boff}$ = 1 mA				
delay time	t_d	<		35 ns
rise time	t_r	<		35 ns



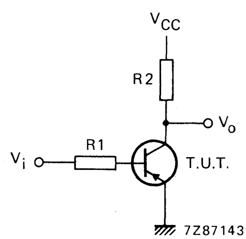


Fig. 2 Waveform and test circuit delay and rise time.
V_i = +0,5 to −10,6 V; $-V_{CC}$ = 3 V; R1 = 10 kΩ; R2 = 275 Ω.
Total shunt capacitance of test jig and connectors = $C_s \leqslant 4$ pF.
Pulse generator: pulse duration 300 ns; fall time < 1 ns; duty factor 2%.

Switching times (between 10% and 90% levels)
$-I_C$ = 10 mA, $-I_{Bon}$ = I_{Boff} = 1 mA

			BSR18	BSR18A	
storage time	t_s	<	200	225	ns
fall time	t_r	<	60	75	ns

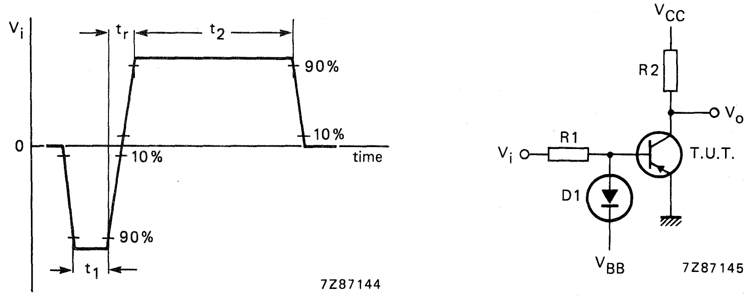


Fig. 3 Waveform and test circuit fall and storage time.
V_i = −9,1 to + 10,9 V; V_{CC} = 3 V; V_{BB} = 0 V (ground); R1 = 10 kΩ; R2 = 275 Ω; D1 = 1N916.
Total shunt capacitance of test jig and connectors = $C_s \leqslant 4$ pF.
Pulse generator: pulse duration t_1 = 10 to 500 μs; rise time $t_r < 1$ ns; duty factor δ = 2%.

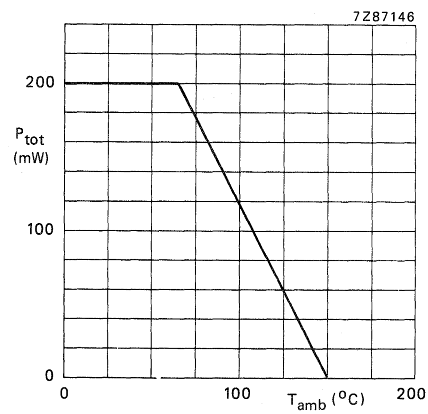


Fig. 4 Power derating curve.

SILICON N-P-N HIGH-VOLTAGE TRANSISTORS

N-P-N high-voltage small-signal transistors for general purposes and especially telephony applications and encapsulated in a SOT-23 envelope.

P-N-P complements are BSR20 and BSR20A.

QUICK REFERENCE DATA

			BSR19	BSR19A	
Collector-base voltage (open emitter)	V_{CBO}	max.	160	180	V
Collector-emitter voltage (open base)	V_{CEO}	max.	140	160	V
Collector current	I_C	max.	600	600	mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	350	350	mW
Junction temperature	T_j	max.	150	150	°C
Collector-emitter saturation voltage I_C = 50 mA; I_B = 5 mA	V_{CEsat}	max.	0,25	0,20	V
D.C. current gain I_C = 10 mA; V_{CE} = 5 V	h_{FE}	min.	60	80	

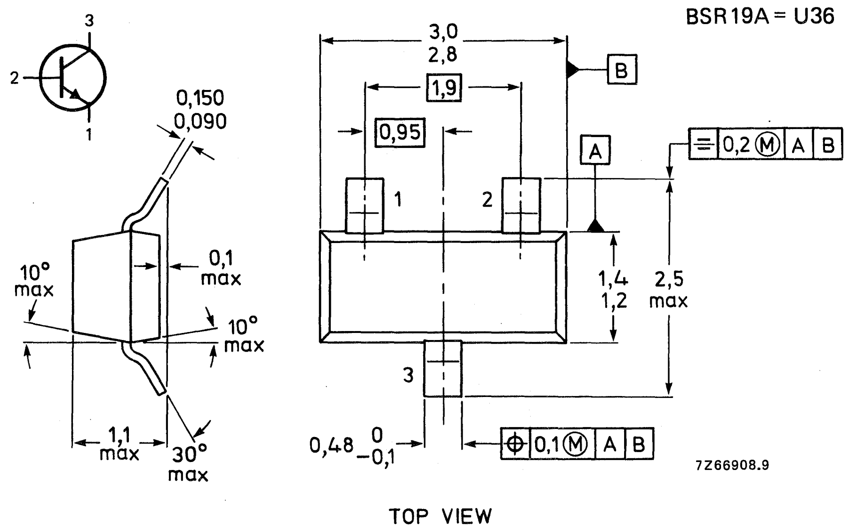
MECHANICAL DATA

Fig. 1 SOT-23.

Dimensions in mm

Marking code

BSR19 = U35
BSR19A = U36



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BSR19	BSR19A	
Collector-base voltage (open emitter)	V_{CBO}	max.	160	180	V
Collector-emitter voltage (open base)	V_{CEO}	max.	140	160	V
Emitter-base voltage (open collector)	V_{EBO}	max.	6		V
Collector current	I_C	max.	600		mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	350		mW
Junction temperature	T_j	max.	150		°C
Storage temperature	T_{stg}		−65 to +150		°C
Thermal resistance*	$R_{th\ j\text{-}t}$		30		K/W
	$R_{th\ t\text{-}s}$		260		K/W
	$R_{th\ s\text{-}a}$		60		K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

			BSR19	BSR19A	
Collector cut-off current					
I_E = 0; V_{CB} = 100 V	I_{CBO}	max.	100		nA
I_E = 0; V_{CB} = 120 V	I_{CBO}	max.		50	nA
I_E = 0; V_{CB} = 100 V; T_{amb} = 100 °C	I_{CBO}	max.	100		μA
I_E = 0; V_{CB} = 120 V; T_{amb} = 100 °C	I_{CBO}	max.		50	μA
Emitter cut-off current					
I_C = 0; V_{EB} = 4,0 V	I_{EBO}	max.	50	50	nA
Breakdown voltages					
I_C = 1,0 mA; I_B = 0	$V_{(BR)CEO}$	min.	140	160	V
I_C = 100 μA; I_E = 0	$V_{(BR)CBO}$	min.	160	180	V
I_C = 0; I_E = 10 μA	$V_{(BR)EBO}$	min.	6,0	6,0	V
Saturation voltages					
I_C = 10 mA; I_B = 1,0 mA	V_{CEsat}	max.	0,15	0,15	V
	V_{BEsat}	max.	1,0	1,0	V
I_C = 50 mA; I_B = 5,0 mA	V_{CEsat}	max.	0,25	0,20	V
	V_{BEsat}	max.	1,2	1,0	V
D.C. current gain					
I_C = 1,0 mA; V_{CE} = 5 V	h_{FE}	min.	60	80	
I_C = 10 mA; V_{CE} = 5 V	h_{FE}	min.	60	80	
		max.	250	250	
I_C = 50 mA; V_{CE} = 5 V	h_{FE}	min.	20	30	
Small-signal current gain					
I_C = 1,0 mA; V_{CE} = 10 V; f = 1 kHz	h_{fe}	min.	50	50	
		max.	200	200	
Output capacitance at f = 1 MHz					
I_E = 0; V_{CB} = 10 V	C_o	max.	6	6	pF

* Substrate size 15 mm x 15 mm x 0,7 mm.

			BSR19	BSR19A	
Input capacitance at f = 1 MHz					
$I_C = 0$; $V_{EB} = 0{,}5$ V	C_i	max.	30	30	pF
Transition frequency at f = 100 MHz					
$I_C = 10$ mA; $V_{CE} = 10$ V	f_T	min.	100	100	MHz
		max.	300	300	MHz
Noise figure at $R_S = 1$ kΩ					
$I_C = 250$ μA; $V_{CE} = 5$ V; f = 10 Hz to 15,7 kHz	F	max.	10	8	dB

SILICON P-N-P HIGH-VOLTAGE TRANSISTORS

P-N-P high-voltage small-signal transistors for general purposes and especially in telephony applications and encapsulated in a SOT-23 envelope.

N-P-N complements are BSR19 and BSR19A.

QUICK REFERENCE DATA

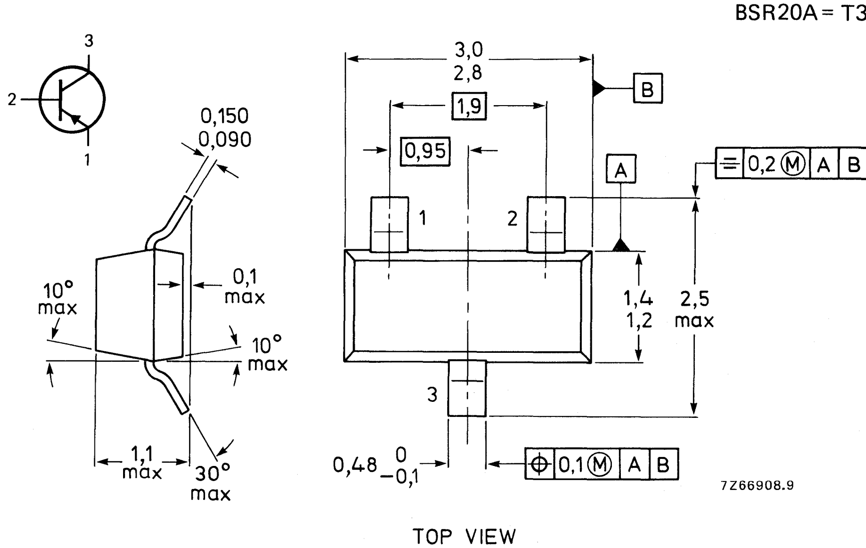
			BSR20	BSR20A	
Collector-base boltage (open emitter)	$-V_{CBO}$	max.	130	160	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	120	150	V
Collector current	$-I_C$	max.	600	600	mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	350	350	mW
Junction temperature	T_j	max.	150	150	°C
Collector-emitter saturation voltage I_C = 50 mA; I_B = 5 mA	V_{CEsat}	max.	0,5	0,5	V
D.C. current gain I_C = 10 mA; V_{CE} = −5 V	h_{FE}	min.	40	60	

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-23.

Marking code
BSR20 = T35
BSR20A = T36



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BSR20	BSR20A	
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	130	160	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	120	150	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5		V
Collector current	$-I_C$	max.	600		mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	350		mW
Junction temperature	T_j	max.	150		°C
Storage temperature	T_{stg}		−65 to +150		°C
Thermal resistance*	$R_{th\ j\text{-}t}$		30		K/W
	$R_{th\ t\text{-}s}$		260		K/W
	$R_{th\ s\text{-}a}$		60		K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

			BSR20	BSR20A	
Collector cut-off current					
$I_E = 0$; $-V_{CB} = 100$ V	$-I_{CBO}$	max.	100		nA
$I_E = 0$; $-V_{CB} = 120$ V	$-I_{CBO}$	max.		50	nA
$I_E = 0$; $-V_{CB} = 100$ V; $T_{amb} = 100$ °C	$-I_{CBO}$	max.	100		μA
$I_E = 0$; $-V_{CB} = 120$ V; $T_{amb} = 100$ °C	$-I_{CBO}$	max.		50	μA
Emitter cut-off current					
$I_C = 0$; $-V_{EB} = 4{,}0$ V	$-I_{EBO}$	max.	50	50	nA
Breakdown voltages					
$I_C = 1{,}0$ mA; $I_B = 0$	$-V_{(BR)CEO}$	min.	120	150	V
$I_C = 100$ μA; $I_E = 0$	$-V_{(BR)CBO}$	min.	130	160	V
$I_C = 0$; $I_E = 10$ μA	$-V_{(BR)EBO}$	min.	5,0	5,0	V
Saturation voltages					
$-I_C = 10$ mA; $-I_B = 1{,}0$ mA	$-V_{CEsat}$	max.	0,2	0,2	V
	$-V_{BEsat}$	max.	1,0	1,0	V
$-I_C = 50$ mA; $-I_B = 5{,}0$ mA	$-V_{CEsat}$	max.	0,5	0,5	V
	$-V_{BEsat}$	max.	1,0	1,0	V
D.C. current gain					
$I_C = 1{,}0$ mA; $-V_{CE} = 5$ V	h_{FE}	min.	30	50	
$I_C = 10$ mA; $-V_{CE} = 5$ V	h_{FE}	min.	40	60	
		max.	180	240	
$I_C = 50$ mA; $-V_{CE} = 5$ V	h_{FE}	min.	40	50	
Small-signal current gain					
$I_C = 1{,}0$ mA; $-V_{CE} = 10$ V; f = 1 kHz	h_{fe}	min.	30	40	
		max.	200	200	
Output capacitance at f = 1 MHz					
$I_E = 0$; $-V_{CB} = 10$ V	C_o	max.	6	6	pF

* Substrate size 15 mm x 15 mm x 0,7 mm.

			BSR20	BSR20A	
Transition frequency at f = 100 MHz $-I_C$ = 10 mA; $-V_{CE}$ = 10 V	f_T	min. max.	100 400	100 300	MHz MHz
Noise figure at R_S = 1 kΩ I_C = 250 μA; $-V_{CE}$ = 5 V; f = 10 Hz to 15,7 kHz	F	max.	8	8	dB

SILICON PLANAR EPITAXIAL TRANSISTORS

P-N-P transistors in miniature plastic envelopes intended for application in thick and thin-film circuits. They are intended for use in telephony and general industrial applications.

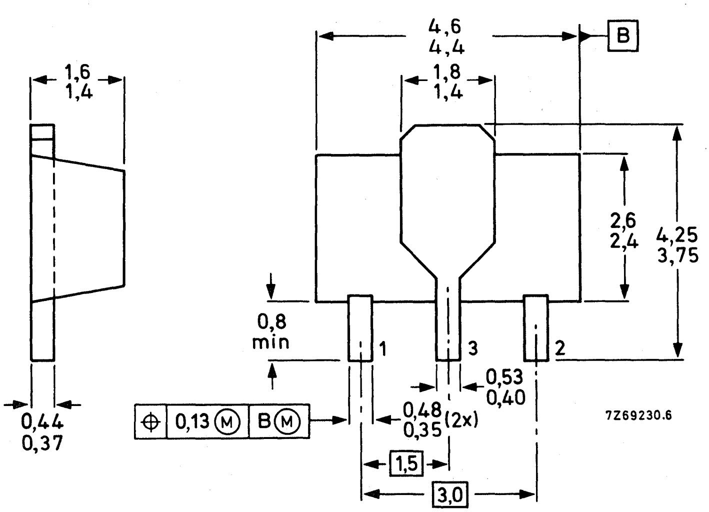
QUICK REFERENCE DATA

			BSR30	BSR31	BSR32	BSR33	
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	70	70	90	90	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	60	60	80	80	V
Collector current (d.c.)	$-I_C$	max.	1	1	1	1	A
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	1	1	1	1	W
Junction temperature	T_j	max.	150	150	150	150	°C
D.C. current gain $-I_C$ = 100 mA; $-V_{CE}$ = 5 V	h_{FE}	>	40	100	40	100	
		<	120	300	120	300	
Transition frequency at f = 35 MHz $-I_C$ = 50 mA; $-V_{CE}$ = 10 V	f_T	>	100	100	100	100	MHz

MECHANICAL DATA

Dimensions in mm

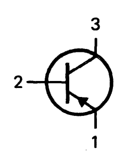
Fig. 1 SOT-89.



BOTTOM VIEW

Mark

BSR30 = BR1
BSR31 = BR2
BSR32 = BR3
BSR33 = BR4



See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BSR30	BSR31	BSR32	BSR33	
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	70	70	90	90	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	60	60	80	80	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5	5	5	5	V

Collector current (d.c.)	$-I_C$	max.	1	A
Base current (d.c.)	$-I_B$	max.	0,1	A
Total power dissipation up to T_{amb} = 25 °C mounted on a ceramic substrate area = 2,5 cm²; thickness = 0,7 mm	P_{tot}	max.	1	W
Storage temperature	T_{stg}		−65 to +150	°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE

From junction to collector tab	$R_{th\ j\text{-}tab}$	=	10	K/W
From junction to ambient in free air mounted on a ceramic substrate area = 2,5 cm²; thickness = 0,7 mm	$R_{th\ j\text{-}a}$	=	125	K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

			BSR30	BSR31	BSR32	BSR33	
Collector cut-off current							
$I_E = 0; -V_{CB} = 60$ V	$-I_{CBO}$	<	100				nA
$I_E = 0; -V_{CB} = 60$ V; $T_j = 150$ °C	$-I_{CBO}$	<	50				μA
Breakdown voltages			BSR30	BSR31	BSR32	BSR33	
$I_B = 0; -I_C = 10$ mA	$-V_{(BR)CEO}$	>	60	60	80	80	V
$V_{BE} = 0; -I_C = 10$ μA	$-V_{(BR)CES}$	>	70	70	90	90	V
$I_C = 0; -I_E = 10$ μA	$-V_{(BR)EBO}$	>	5	5	5	5	V
Saturation voltages *							
$-I_C = 150$ mA; $-I_B = 15$ mA	$-V_{CEsat}$	<	0,25	0,25	0,25	0,25	V
	$-V_{BEsat}$	<	1,0	1,0	1,0	1,0	V
$-I_C = 500$ mA; $-I_B = 50$ mA	$-V_{CEsat}$	<	0,5	0,5	0,5	0,5	V
	$-V_{BEsat}$	<	1,2	1,2	1,2	1,2	V
D.C. current gain *							
$-I_C = 100$ μA; $V_{CE} = 5$ V	h_{FE}	>	10	30	10	30	
$-I_C = 100$ mA; $V_{CE} = 5$ V	h_{FE}	>	40	100	40	100	
		<	120	300	120	300	
$-I_C = 500$ mA; $V_{CE} = 5$ V	h_{FE}	>	30	50	30	50	
Transition frequency at f = 35 MHz							
$-I_C = 50$ mA; $-V_{CE} = 10$ V	f_T	>	100				MHz
Collector capacitance at f = 1 MHz							
$I_E = I_e = 0; -V_{CB} = 10$ V	C_c	<	20				pF
Emitter capacitance at f = 1 MHz							
$I_C = I_c = 0; -V_{EB} = 0,5$ V	C_e	<	120				pF

Switching times see next page.

* Measured under pulse conditions: $t_p = 300$ μs; $\delta < 0,01$.

CHARACTERISTICS (continued)

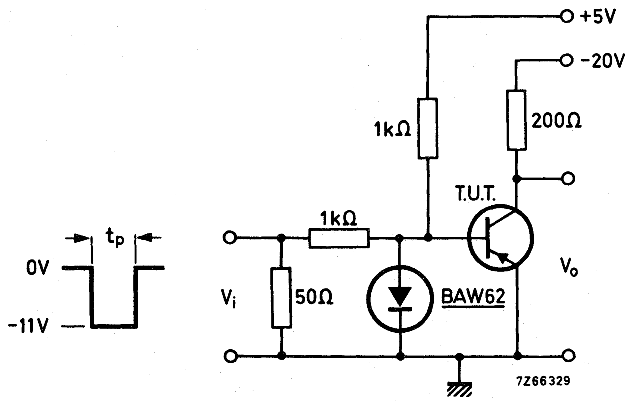
T_{amb} = 25 °C

Switching times

$-I_{Con}$ = 100 mA; $-I_{Bon}$ = $+I_{Boff}$ = 5 mA

Turn-on time	t_{on}	<	500	ns
Turn-off time	t_{off}	<	650	ns

Test circuit



Pulse generator:

Pulse duration	t_p = 10 μs
Rise time	t_r ≤ 15 ns
Fall time	t_f ≤ 15 ns
Source impedance	Z_S = 50 Ω

Oscilloscope:

Rise time	t_r ≤ 15 ns
Input impedance	Z_I ≥ 100 kΩ

SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N transistors in miniature plastic envelopes intended for application in thick and thin-film circuits. They are intended for use in telephony and general industrial applications.

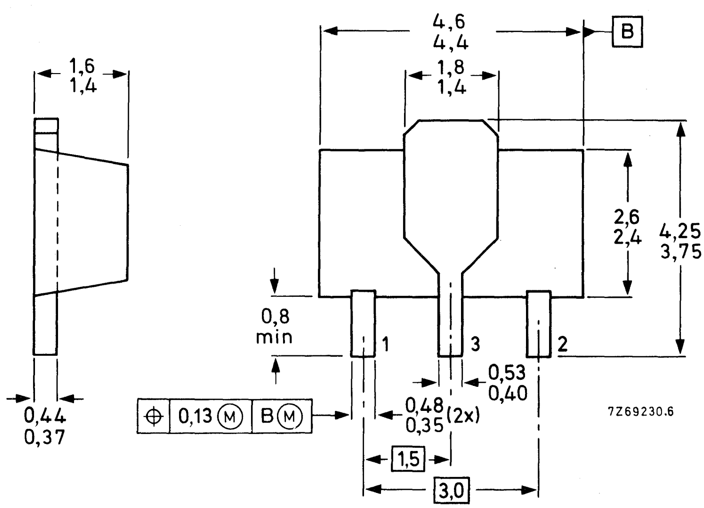
QUICK REFERENCE DATA

			BSR40	BSR41	BSR42	BSR43	
Collector-base voltage (open emitter)	V_{CBO}	max.	70	70	90	90	V
Collector-emitter voltage (open base)	V_{CEO}	max.	60	60	80	80	V
Collector current (d.c.)	I_C	max.	1	1	1	1	A
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	1	1	1	1	W
Junction temperature	T_j	max.	150	150	150	150	°C
D.C. current gain I_C = 100 mA; V_{CE} = 5 V	h_{FE}	> <	40 120	100 300	40 120	100 300	
Transition frequency at f = 35 MHz I_C = 50 mA; V_{CE} = 10 V	f_T	>	100	100	100	100	MHz

MECHANICAL DATA

Dimensions in mm

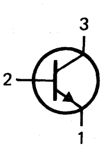
Fig. 1 SOT-89.



BOTTOM VIEW

Mark

BSR40 = AR1
BSR41 = AR2
BSR42 = AR3
BSR43 = AR4



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BSR40	BSR41	BSR42	BSR43	
Collector-base voltage (open emitter)	V_{CBO}	max.	70	70	90	90	V
Collector-emitter voltage (open base)	V_{CEO}	max.	60	60	80	80	V
Emitter-base voltage (open collector)	V_{EBO}	max.	5	5	5	5	V

Collector current (d.c.)	I_C	max.	1	A
Base current (d.c.)	I_B	max.	0,1	A
Total power dissipation up to T_{amb} = 25 °C mounted on a ceramic substrate area = 2,5 cm^2; thickness = 0,7 mm	P_{tot}	max.	1	W
Storage temperature	T_{stg}		−65 to +150	°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE

From junction to collector tab	$R_{th\ j\text{-}tab}$	=	10	K/W
From junction to ambient in free air mounted on a ceramic substrate area = 2,5 cm^2; thickness = 0,7 m	$R_{th\ j\text{-}a}$	=	125	K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Collector cut-off current							
$I_E = 0$; $V_{CB} = 60$ V	I_{CBO}	<	100				nA
$I_E = 0$; $V_{CB} = 60$ V; $T_j = 150$ °C	I_{CBO}	<	50				μA
Breakdown voltages			BSR40	BSR41	BSR42	BSR43	
$I_B = 0$; $I_C = 10$ mA	$V_{(BR)CEO}$	>	60	60	80	80	V
$V_{BE} = 0$; $I_C = 10$ μA	$V_{(BR)CES}$	>	70	70	90	90	V
$I_C = 0$; $I_E = 10$ μA	$V_{(BR)EBO}$	>	5	5	5	5	V
Saturation voltages *							
$I_C = 150$ mA; $I_B = 15$ mA	V_{CEsat}	<	0,25	0,25	0,25	0,25	V
	V_{BEsat}	<	1,0	1,0	1,0	1,0	V
$I_C = 500$ mA; $I_B = 50$ mA	V_{CEsat}	<	0,5	0,5	0,5	0,5	V
	V_{BEsat}	<	1,2	1,2	1,2	1,2	V
D.C. current gain *							
$I_C = 100$ μA; $V_{CE} = 5$ V	h_{FE}	>	10	30	10	30	
$I_C = 100$ mA; $V_{CE} = 5$ V	h_{FE}	>	40	100	40	100	
		<	120	300	120	300	
$I_C = 500$ mA; $V_{CE} = 5$ V	h_{FE}	>	30	50	30	50	
Transition frequency at f = 35 MHz							
$I_C = 50$ mA; $V_{CE} = 10$ V	f_T	>	100				MHz
Collector capacitance at f = 1 MHz							
$I_E = I_e = 0$; $V_{CB} = 10$ V	C_c	<	12				pF
Emitter capacitance at f = 1 MHz							
$I_C = I_c = 0$; $V_{EB} = 0,5$ V	C_e	<	90				pF

Switching times see next page.

* Measured under pulse conditions: t_p = 300 μs; $\delta < 0,01$.

CHARACTERISTICS (continued)

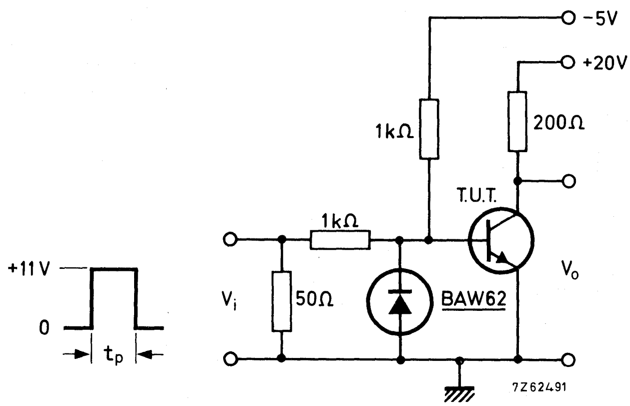
T_{amb} = 25 °C

Switching times

I_{Con} = 100 mA; $I_{Bon} = -I_{Boff}$ = 5 mA

Turn-on time	t_{on}	<	250	ns
Turn-off time	t_{off}	<	1000	ns

Test circuit



Pulse generator:

Pulse duration	t_p = 10 μs
Rise time	$t_r \leqslant 15$ ns
Fall time	$t_f \leqslant 15$ ns
Source impedance	Z_S = 50 Ω

Oscilloscope:

Rise time	$t_r \leqslant 15$ ns
Input impedance	$Z_I \geqslant 100$ kΩ

N-CHANNEL FETS

Silicon n-channel depletion type junction field-effect transistors in a plastic microminiature envelope intended for application in thick and thin-film circuits. The transistors are intended for low-power, chopper or switching applications in industrial service.

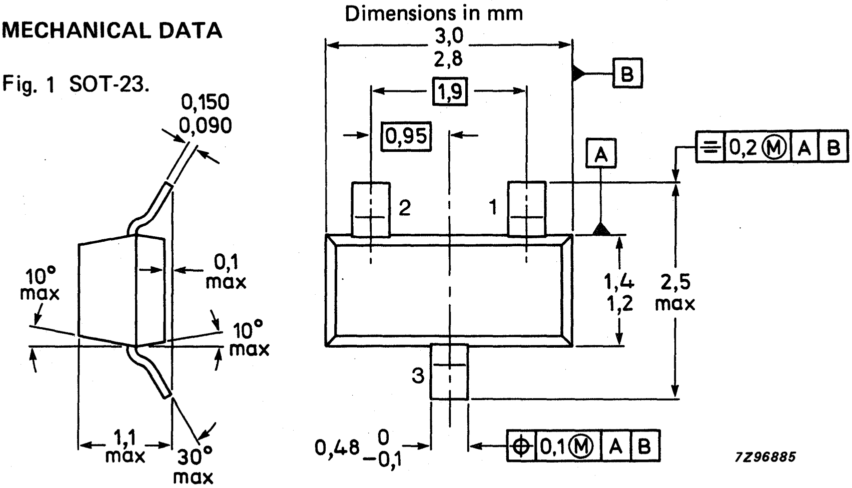
QUICK REFERENCE DATA

			BSR56	BSR57	BSR58	
Drain-source voltage	$\pm V_{DS}$	max.	40	40	40	V
Total power dissipation up to T_{amb} = 65 °C	P_{tot}	max.	250	250	250	mW
Drain current V_{DS} = 15 V; V_{GS} = 0	I_{DSS}	>	50	20	8	mA
		<	–	100	80	mA
Gate-source cut-off voltage V_{DS} = 15 V; I_D = 0,5 nA	$-V_{(P)GS}$	>	4	2	0,8	V
		<	10	6	4	V
Drain-source resistance (on) at f = 1 kHz I_D = 0; V_{GS} = 0	$r_{ds\ on}$	<	25	40	60	Ω
Feedback capacitance at f = 1 MHz $-V_{GS}$ = 10 V; V_{DS} = 0	C_{rs}	<	5	5	5	pF
Turn-off time V_{DD} = 10 V; V_{GS} = 0						
I_D = 20 mA; $-V_{GSM}$ = 10 V	t_{off}	<	25	–	–	ns
I_D = 10 mA; $-V_{GSM}$ = 6 V	t_{off}	<	–	50	–	ns
I_D = 5 mA; $-V_{GSM}$ = 4 V	t_{off}	<	–	–	100	ns

MECHANICAL DATA

Dimensions in mm

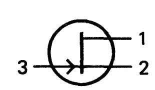
Fig. 1 SOT-23.



See also *Soldering Recommendations*. TOP VIEW

Marking code

BSR56 = M4
BSR57 = M5
BSR58 = M6



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage (See Fig. 4)	$\pm V_{DS}$	max.	40 V
Drain-gate voltage (See Fig. 4)	V_{DGO}	max.	40 V
Gate-source voltage (See Fig. 4)	$-V_{GSO}$	max.	40 V
Forward gate current	I_{GF}	max.	50 mA
Total power dissipation up to T_{amb} = 65 °C	P_{tot}	max.	250 mW
Storage temperature range	T_{stg}		−55 to + 175 °C
Junction temperature	T_j	max.	175 °C

THERMAL CHARACTERISTICS*

$T_j = P (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	60 K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280 K/W
From soldering points to ambient**	$R_{th\ s\text{-}a}$	=	90 K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Gate-source cut-off current V_{DS} = 0 V; $-V_{GS}$ = 20 V	$-I_{GSS}$	<	1	nA
Drain cut-off current V_{DS} = 15 V; $-V_{GS}$ = 10 V	I_{DSX}	<	1	nA

			BSR56	BSR57	BSR58	
Drain current ▲ V_{DS} = 15 V; V_{GS} = 0	I_{DSS}	>	50	20	8	mA
		<	–	100	80	mA
Gate-source breakdown voltage $-I_G$ = 1 μA; V_{DS} = 0	$-V_{(BR)GSS}$	>	40	40	40	V
Gate-source cut-off voltage I_D = 0,5 nA; V_{DS} = 15 V	$-V_{(P)GS}$	>	4	2	0,8	V
		<	10	6	4	V
Drain-source voltage (on) I_D = 20 mA; V_{GS} = 0	V_{DSon}	<	750	–	–	mV
I_D = 10 mA; V_{GS} = 0	V_{DSon}	<	–	500	–	mV
I_D = 5 mA; V_{GS} = 0	V_{DSon}	<	–	–	400	mV
Drain-source resistance (on) at f = 1 kHz I_D = 0; V_{GS} = 0	$r_{ds\ on}$	<	25	40	60	Ω

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

▲ Measured under pulsed conditions; t_p = 100 ms; $\delta \leqslant 0{,}1$.

			BSR56	BSR57	BSR58
Switching times*					
V_{DD} = 10 V; V_{GS} = 0					
Conditions I_D and $-V_{GSM}$	I_D	=	20	10	5 mA
	$-V_{GSM}$	=	10	6	4 V
Delay time	t_d	<	6	6	10 ns
Rise time	t_r	<	3	4	10 ns
Turn-off time	t_{off}	<	25	50	100 ns

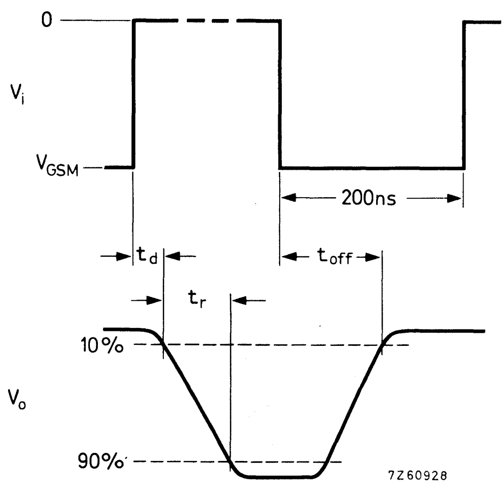


Fig. 2 Switching times waveforms.

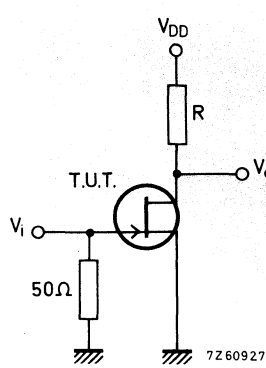


Fig. 3 Test circuit.

BSR56; R = 464 Ω
BSR57; R = 953 Ω
BSR58; R = 1910 Ω

Pulse generator

$t_r = t_f \leqslant 1$ ns
δ = 0,02
Z_o = 50 Ω

Oscilloscope

$t_r \leqslant 0{,}75$ ns
$R_i \geqslant 1$ MΩ
$C_i \leqslant 2{,}5$ pF

* Switching times measured on devices in SOT-18 envelope.

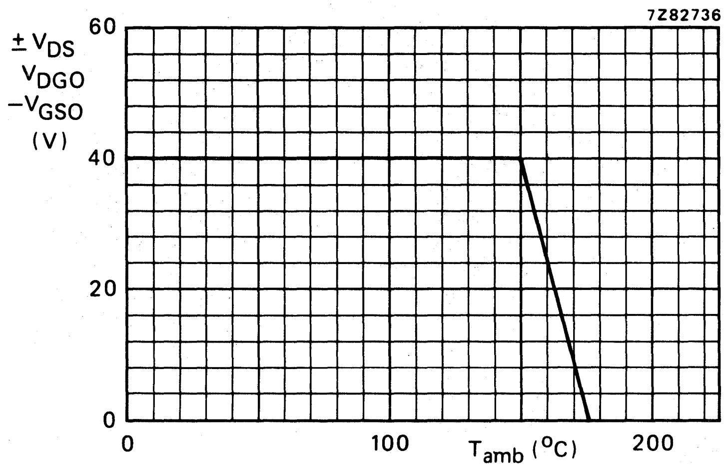


Fig. 4 Voltage derating curve.

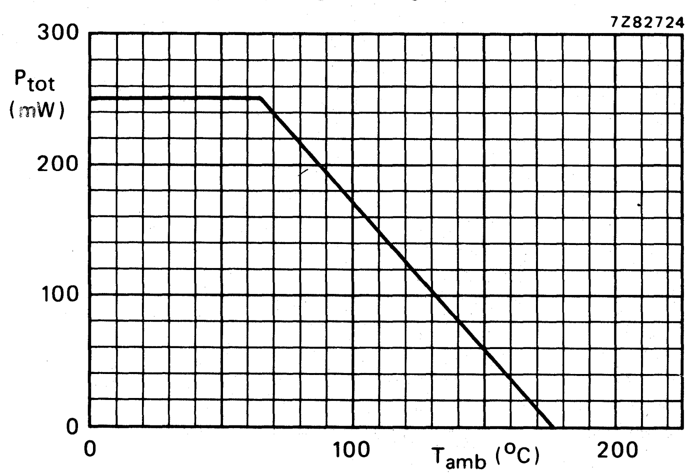


Fig. 5 Power derating curve.

HIGH VOLTAGE P-N-P TRANSISTORS

Silicon planar epitaxial transistor in a microminiature plastic envelope intended for application in thick and thin-film circuits. This transistor is intended for high voltage general purpose and switching applications.

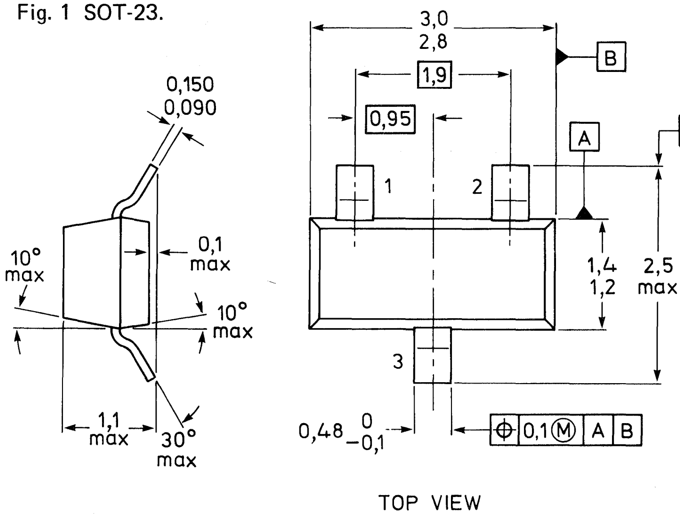
QUICK REFERENCE DATA

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	110 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	100 V
Collector current (peak value)	$-I_{CM}$	max.	100 mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	350 mW
Junction temperature	T_j	max.	175 °C
D.C. current gain at T_j = 25 °C $-I_C$ = 25 mA; $-V_{CE}$ = 5 V	h_{FE}	>	30
Transition frequency at f = 35 MHz $-I_C$ = 25 mA; $-V_{CE}$ = 5 V	f_T	> typ.	50 MHz 85 MHz

MECHANICAL DATA

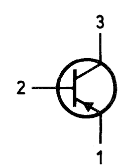
Dimensions in mm

Fig. 1 SOT-23.

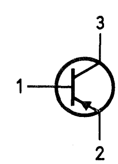


Marking code

BSS63 = T3



BSS63R = T6



R-types are available on request

See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter) see Fig. 6 $-I_C = 10\ \mu A$	$-V_{CBO}$	max.	110 V
Collector-emitter voltage (open base) see Fig. 6 $-I_C = 100\ \mu A$	$-V_{CEO}$	max.	100 V
Emitter-base voltage (open collector) see Fig. 6 $-I_E = 10\ \mu A$	$-V_{EBO}$	max.	6 V
Collector current (d.c.)	$-I_C$	max.	100 mA
Collector current (peak value)	$-I_{CM}$	max.	100 mA
Base current (peak value)	$-I_{BM}$	max.	100 mA
Total power dissipation up to T_{amb} = 25 °C **	P_{tot}	max.	350 mW
Storage temperature	T_{stg}		−65 to + 175 °C
Junction temperature	T_j	max.	175 °C

THERMAL CHARACTERISTICS *

$T_j = Px\ (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	50 K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280 K/W
From soldering points to ambient **	$R_{th\ s\text{-}a}$	=	90 K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current $I_E = 0;\ -V_{CB} = 90\ V$	$-I_{CBO}$	<	100 nA
$I_E = 0;\ -V_{CB} = 90\ V;\ T_j = 150\ °C$	$-I_{CBO}$	<	50 μA
Emitter cut-off current $I_C = 0;\ -V_{EB} = 6\ V$	$-I_{EBO}$	<	200 nA
Saturation voltage $-I_C = 25\ mA;\ -I_B = 2{,}5\ mA$	$-V_{CEsat}$ $-V_{BEsat}$	< <	250 mV 900 mV
D.C. current gain $-I_C = 10\ mA;\ -V_{CE} = 1\ V$ $-I_C = 25\ mA;\ -V_{CE} = 1\ V$	h_{FE} h_{FE}	> >	30 30
Collector capacitance at f = 1 MHz $I_E = I_e = 0;\ -V_{CB} = 10\ V$	C_c	typ.	3 pF
Transition frequency at f = 35 MHz $-I_C = 25\ mA;\ -V_{CE} = 5\ V$	f_T	> typ.	50 MHz 85 MHz

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

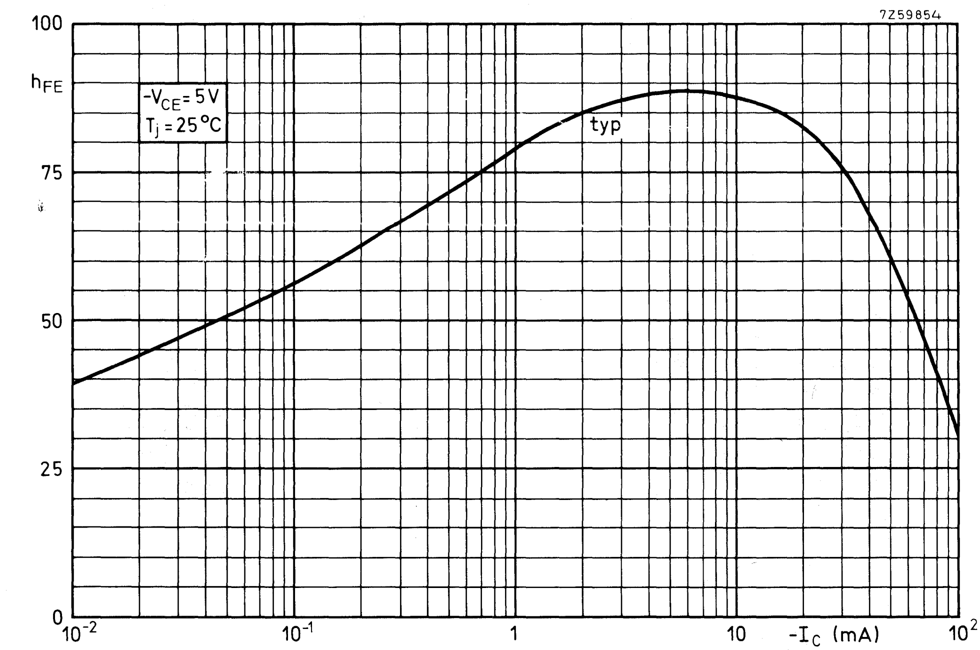

7Z59854
100
h_{FE}
$-V_{CE} = 5\,V$
$T_j = 25\,°C$
typ
75
50
25
0
10^{-2}
10^{-1}
1
10
$-I_C$ (mA)
10^2

Fig. 2.

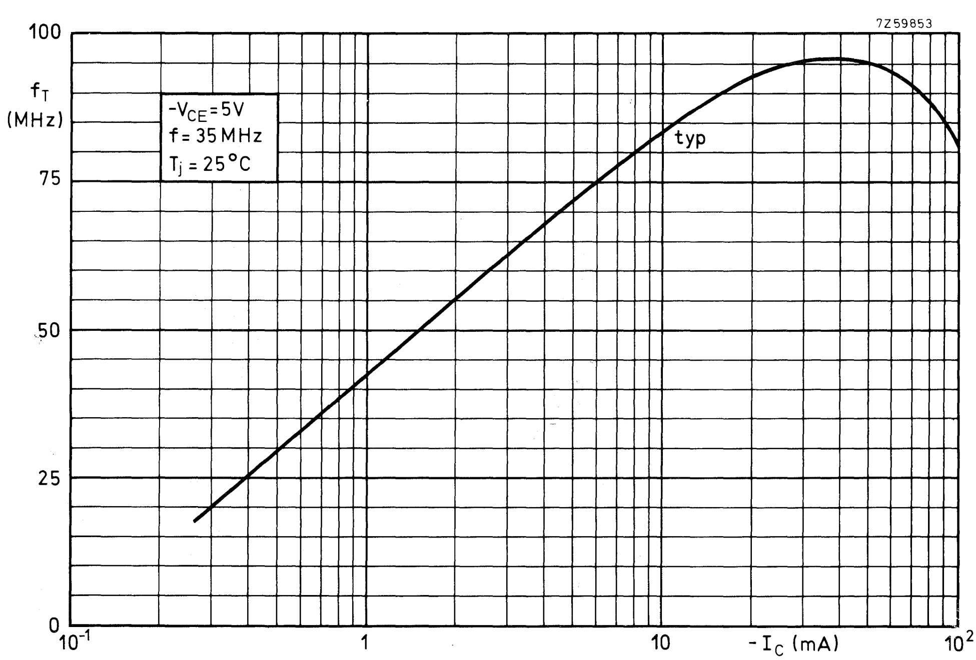

7Z59853
100
f_T
(MHz)
$-V_{CE} = 5\,V$
$f = 35\,MHz$
$T_j = 25\,°C$
typ
75
50
25
0
10^{-1}
1
10
$-I_C$ (mA)
10^2

Fig. 3.

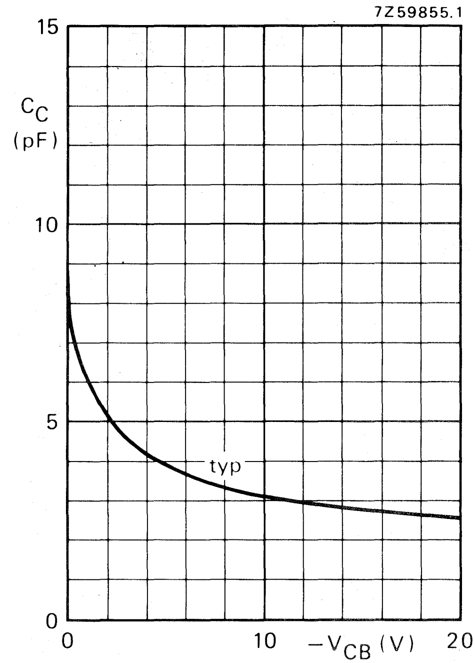


Fig. 4 Typical values collector capacitance as a function of collector-base voltage.
$I_E = I_e = 0$; $T_j = 25\ ^oC$; f = 1 MHz.

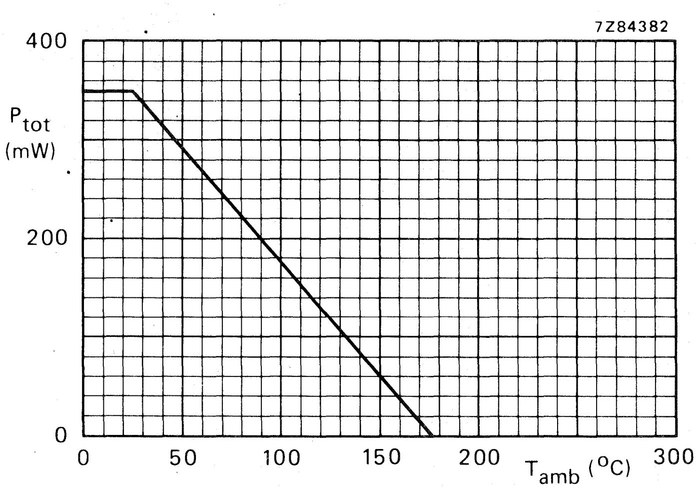


Fig. 5 Power derating curve.

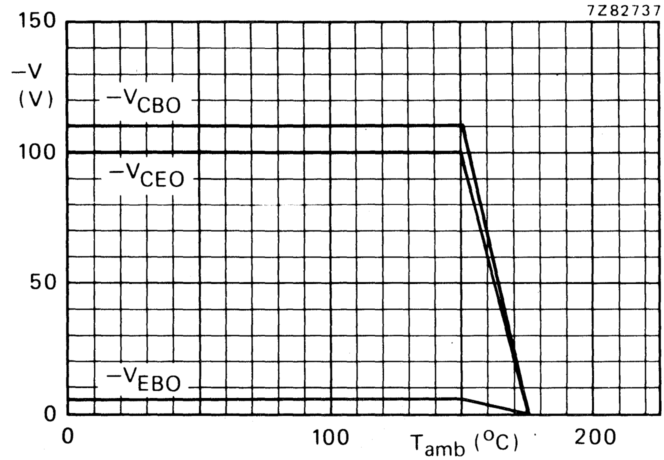


Fig. 6 Voltage derating curves.

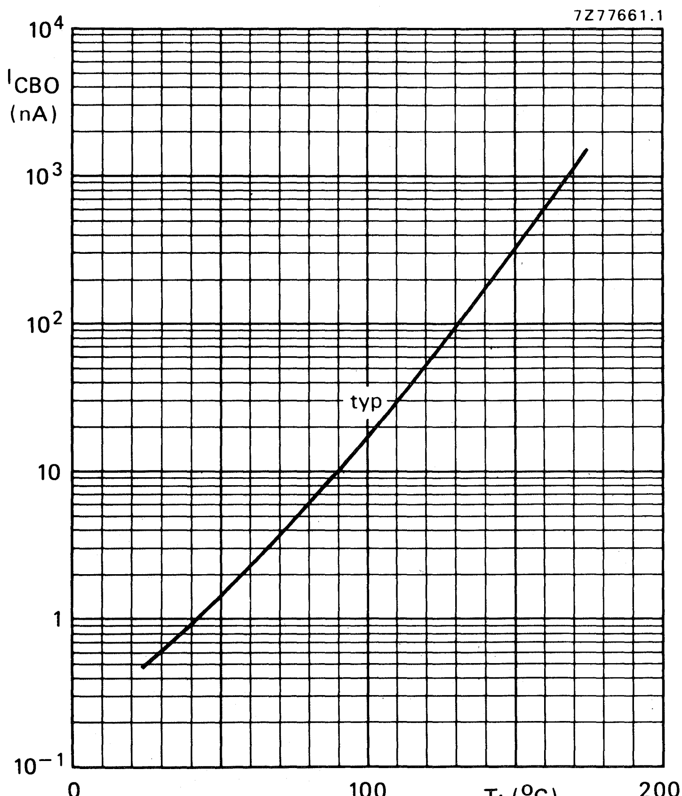


Fig. 7 Typical values collector-base currents as a function of the junction temperature at a collector-base voltage of 90 V.

HIGH VOLTAGE N-P-N TRANSISTORS

Silicon planar epitaxial transistor in a microminiature plastic envelope intended for application in thick and thin-film circuits. This transistor is intended for high-voltage general purpose and switching applications.

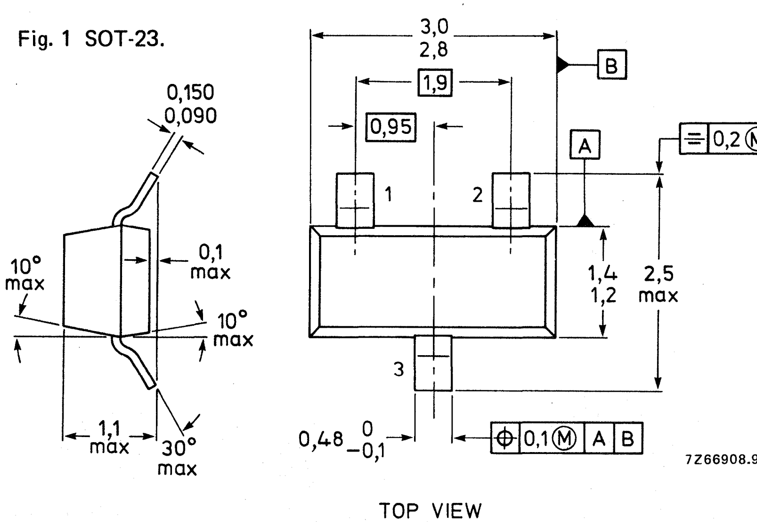
QUICK REFERENCE DATA

Collector-base voltage (open emitter)	V_{CBO}	max.	120	V
Collector-emitter voltage (open base)	V_{CEO}	max.	80	V
Collector current (peak value)	I_{CM}	max.	250	mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	350	mW
Junction temperature	T_j	max.	175	°C
D.C. current gain I_C = 10 mA; V_{CE} = 1 V; T_j = 25 °C	h_{FE}	> typ.	20 80	
Transition frequency at f = 35 MHz I_C = 4 mA; V_{CE} = 10 V	f_T	>	60	MHz
Turn-off time I_C = 15 mA; I_{Bon} = $-I_{Boff}$ = 1 mA	t_{off}	<	1	μs

MECHANICAL DATA

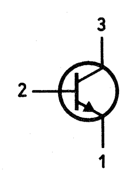
Dimensions in mm

Fig. 1 SOT-23.

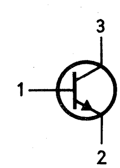


Marking code

BSS64 = U3



BSS64R = U6



R-types are available on request

See also *Soldering recommendations*.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter) see Fig. 2 $I_C = 100\ \mu A$	V_{CBO}	max.	120 V
Collector-emitter voltage (open base) see Fig. 2 $I_C = 4$ mA	V_{CEO}	max.	80 V
Emitter-base voltage (open collector) see Fig. 2 $I_E = 100\ \mu A$	V_{EBO}	max.	5 V
Collector current (d.c. or averaged over any 20 ms period)	I_C	max.	100 mA
Collector current (peak value)	I_{CM}	max.	250 mA
Base current (peak value)	I_{BM}	max.	100 mA
Total power dissipation up to $T_{amb} = 25\ ^oC$ **	P_{tot}	max.	350 mW
Storage temperature	T_{stg}	−65 to	+ 175 °C
Junction temperature	T_j	max.	175 °C

THERMAL CHARACTERISTICS *

$T_j = Px\ (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	50 K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280 K/W
From soldering points to ambient **	$R_{th\ s\text{-}a}$	=	90 K/W

CHARACTERISTICS

$T_j = 25\ ^oC$ unless otherwise specified

Collector cut-off current $I_E = 0$; $V_{CB} = 90$ V	I_{CBO}	<	100 nA
$I_E = 0$; $V_{CB} = 90$ V; $T_j = 150\ ^oC$	I_{CBO}	<	50 μA
Emitter cut-off current $I_C = 0$; $V_{EB} = 5$ V	I_{EBO}	typ. <	0,5 nA 200 nA
Saturation voltages $I_C = 4$ mA; $I_B = 400\ \mu A$	V_{CEsat} V_{BEsat}	< <	150 mV 1200 mV
$I_C = 50$ mA; $I_B = 15$ mA	V_{CEsat}	<	200 mV
D.C. current gain $I_C = 1$ mA; $V_{CE} = 1$ V	h_{FE}	typ.	60
$I_C = 10$ mA; $V_{CE} = 1$ V	h_{FE}	> typ.	20 80
$I_C = 20$ mA; $V_{CE} = 1$ V	h_{FE}	typ.	55

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

Transition frequency at f = 35 MHz I_C = 4 mA; V_{CE} = 10 V	f_T	> typ.	60 MHz 100 MHz
Collector capacitance at f = 1 MHz $I_E = I_e = 0$; V_{CB} = 10 V	C_c	typ.	3 pF ←
Turn-off switching time I_{Con} = 15 mA; $I_{Bon} = -I_{Boff}$ = 1 mA	t_{off}	<	1 μs

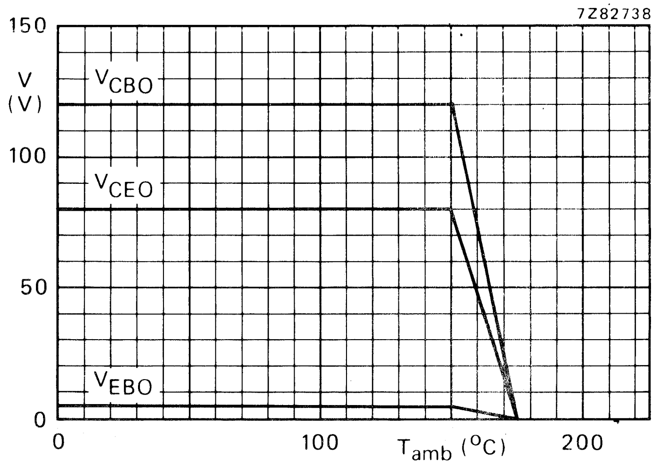


Fig. 2 Voltage derating curves.

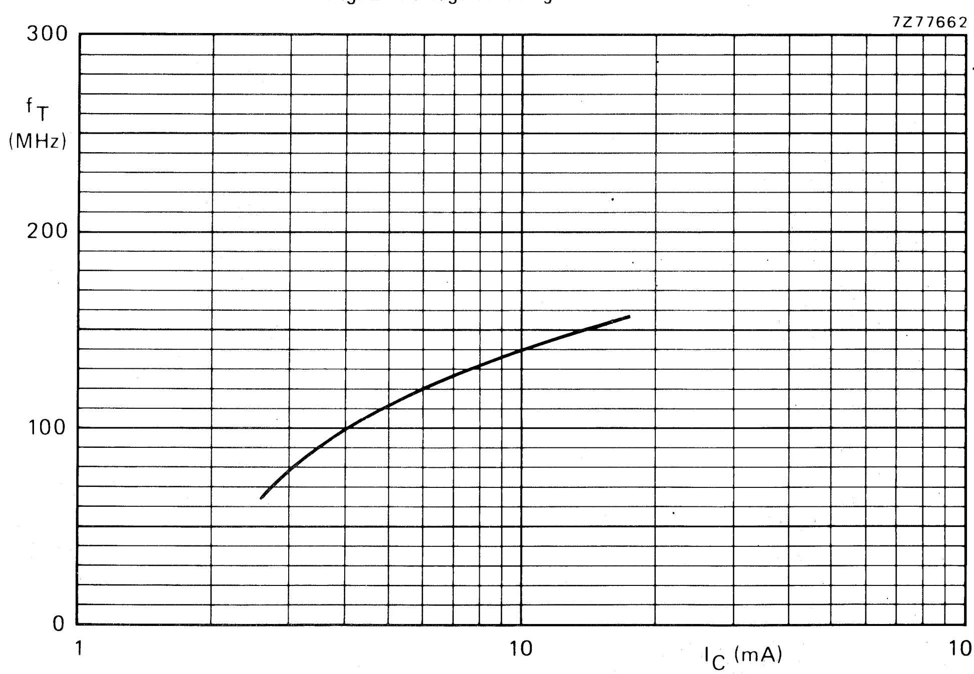


Fig. 3 Typical values transition frequency. V_{CE} = 10 V; f = 35 MHz; T_j = 25 °C.

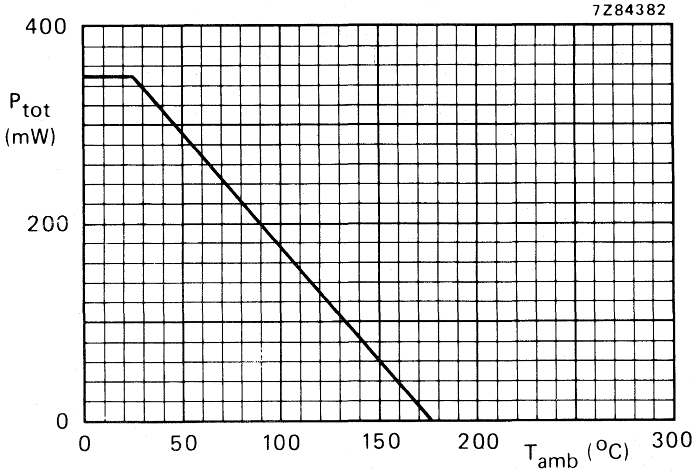


Fig. 4 Power derating curve.

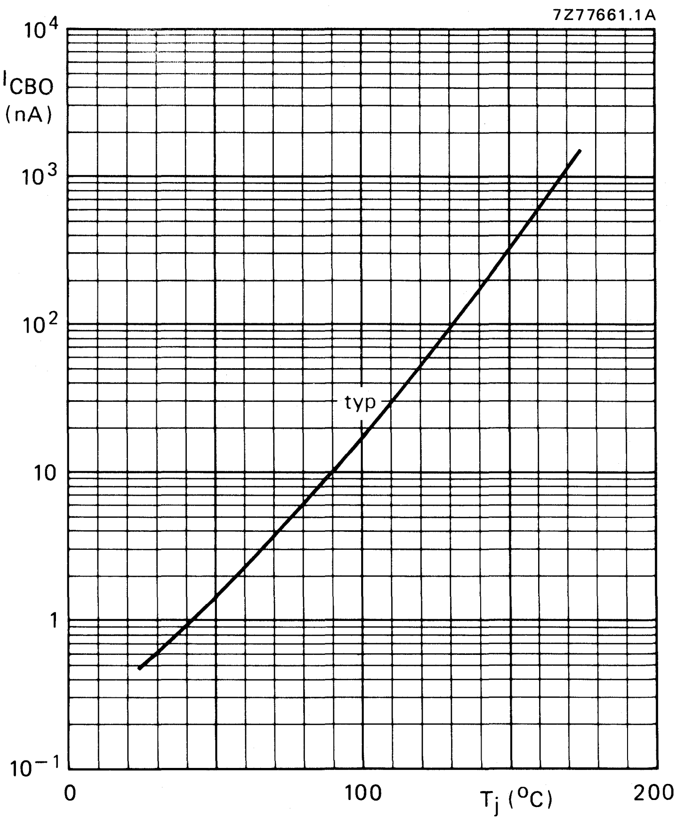


Fig. 5 Typical values collector-base current as a function of the junction temperature at a collector-base voltage of −90 V.

MOSFET N-CHANNEL ENHANCEMENT SWITCHING TRANSISTOR

Symmetrical insulated-gate silicon MOS field-effect transistor of the N-channel enhancement mode type.

The transistor is sealed in a SOT-143 envelope and features a low ON resistance and low capacitances.

The transistor is protected against excessive input voltages by integrated back-to-back diodes between gate and substrate.

Applications:

- analog and/or digital switch
- switch driver

QUICK REFERENCE DATA

Drain-source voltage	V_{DS}	max.	10 V
Source-drain voltage	V_{SD}	max.	10 V
Drain-substrate voltage	V_{DB}	max.	15 V
Source-substrate voltage	V_{SB}	max.	15 V
Drain current (d.c.)	I_D	max.	50 mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	230 mW
Gate-source cut-off voltage $V_{DS} = V_{GS}$; $V_{SB} = 0$; $I_D = 1\ \mu A$	$V_{(P)GS}$	$>$ $<$	0,1 V 2,0 V
Drain-source ON-resistance $V_{GS} = 10$ V; $V_{SB} = 0$; $I_D = 0,1$ mA	$R_{DS(on)}$	$<$	45 Ω
Feed-back capacitance $V_{GS} = V_{BS} = -15$ V; $V_{DS} = 10$ V; f = 1 MHz	C_{rss}	typ.	0,6 pF

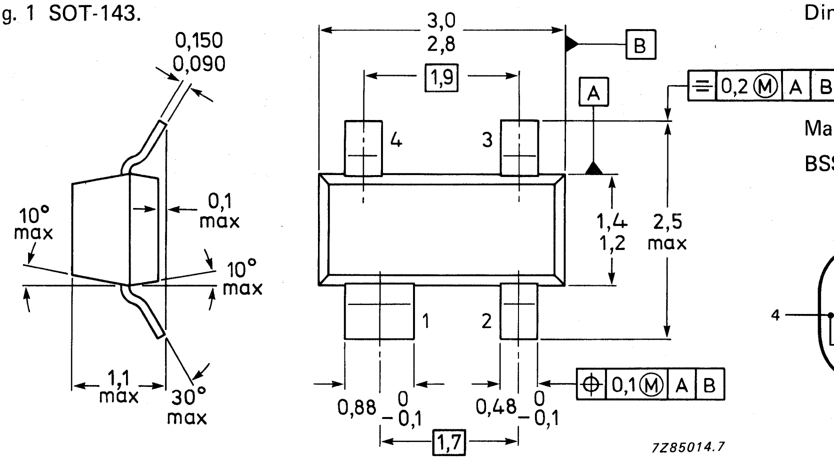
MECHANICAL DATA

SOT-143 (see Fig. 1).

See also *Soldering recommendations*.

Fig. 1 SOT-143.

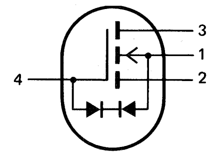
Dimensions in mm



TOP VIEW

Marking code:

BSS83 = M74



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	V_{DS}	max.	10 V
Source-drain voltage	V_{SD}	max.	10 V
Drain-substrate voltage	V_{DB}	max.	15 V
Source-substrate voltage	V_{SB}	max.	15 V
Drain current (d.c.)	I_D	max.	50 mA
Total power dissipation up to T_{amb} = 25 °C*	P_{tot}	max.	230 mW*
Storage temperature range	T_{stg}		−65 to + 150 °C
Junction temperature	T_j	max.	125 °C

THERMAL RESISTANCE

From junction to ambient in free air*	$R_{th\ j\text{-}a}$	=	430 K/W*

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Drain-source breakdown voltage $V_{GS} = V_{BS} = -5$ V; I_D = 10 nA	$V_{(BR)DSX}$	>	10 V
Source-drain breakdown voltage $V_{GD} = V_{BD} = -5$ V; I_D = 10 nA	$V_{(BR)SDX}$	>	10 V
Drain-substrate breakdown voltage → V_{DB} = 0; I_D = 10 nA; open source	$V_{(BR)DBO}$	>	15 V
Source-substrate breakdown voltage → V_{DB} = 0; I_D = 10 nA; open drain	$V_{(BR)SBO}$	>	15 V
Drain-source leakage current $V_{GS} = V_{BS} = -2$ V; V_{DS} = 6,6 V	I_{DSoff}	<	10 nA

→ * Device mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

Source-drain leakage current $V_{GD} = V_{BD} = -2$ V; $V_{SD} = 6,6$ V	I_{SDoff}	<	10 nA ←
Forward transconductance at f = 1 kHz $V_{DS} = 10$ V; $V_{SB} = 0$; $I_D = 20$ mA	g_{fs}	> typ.	10 mS 15 mS
Gate-source cut-off voltage $V_{DS} = V_{GS}$; $V_{SB} = 0$; $I_D = 1$ μA	$V_{(P)GS}$	> <	0,1 V 2,0 V
Drain-source ON-resistance $I_D = 0,1$ mA;			
$V_{GS} = 5$ V; $V_{SB} = 0$	$R_{DS(on)}$	<	70 Ω
$V_{GS} = 10$ V; $V_{SB} = 0$	$R_{DS(on)}$	<	45 Ω
$V_{GS} = 3,2$ V; $V_{SB} = 6,8$ V (see Fig. 4)	$R_{DS(on)}$	typ. <	80 Ω 120 Ω
Gate-substrate zener voltages			
$V_{DB} = V_{SB} = 0$; $-I_C = 10$ μA	$V_{Z(1)}$	>	12,5 V
$V_{DB} = V_{SB} = 0$; $+I_G = 10$ μA	$V_{Z(2)}$	>	12,5 V
Capacitances at f = 1 MHz $V_{GS} = V_{BS} = -15$ V; $V_{DS} = 10$ V			
Feed-back capacitance	C_{rss}	typ.	0,6 pF
Input capacitance	C_{iss}	typ.	1,5 pF
Output capacitance	C_{oss}	typ.	1,0 pF
Switching times (see Fig. 2) $V_{DD} = 10$ V; $V_i = 5$ V	t_{on}	typ.	1,0 ns
	t_{off}	typ.	5,0 ns

Pulse generator:

R_i	=	50 Ω
t_r	<	0,5 ns
t_f	<	1,0 ns
t_p	=	20 ns
δ	<	0,01

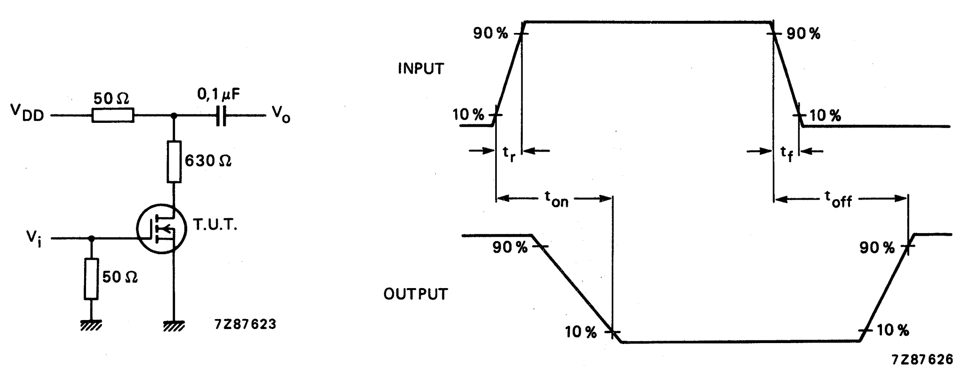


Fig. 2 Switching times test circuit and input and output waveforms.

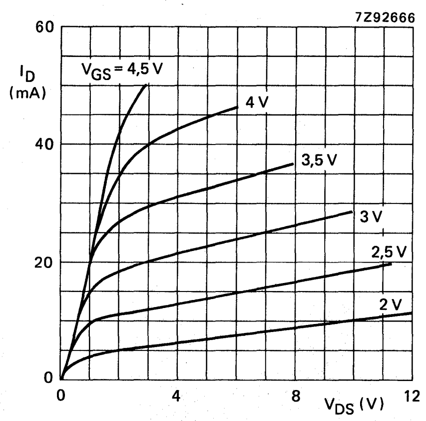


Fig. 3 V_{SB} = 0; typical values.

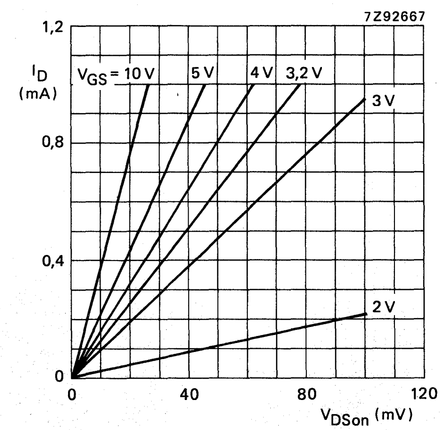


Fig. 4 V_{SB} = 6,8 V; typical values.

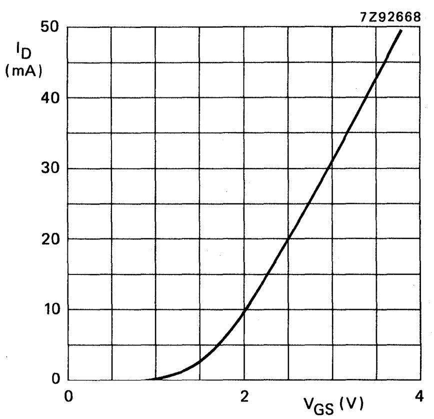


Fig. 5 V_{DS} = 10 V; V_{BS} = 0; typical values.

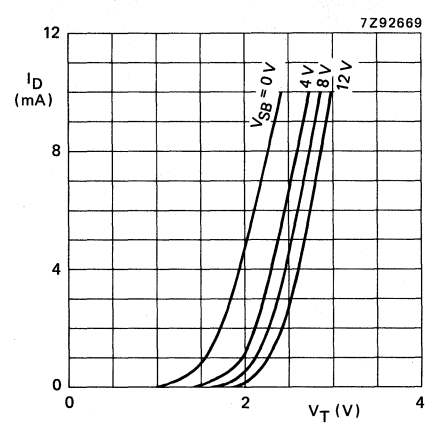


Fig. 6 $V_{DS} = V_{GS} = V_T$.

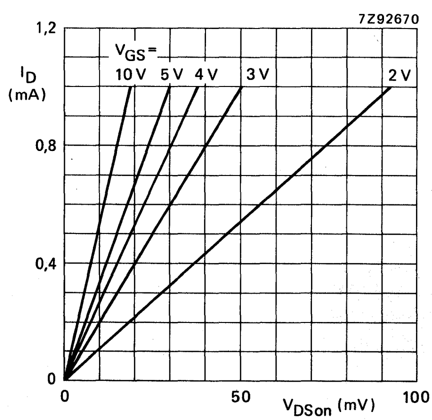


Fig. 7 V_{SB} = 0; typical values.

Conditions for Figs 3, 4, 5, 6 and 7:
T_j = 25 °C.

SILICON PLANAR EPITAXIAL TRANSISTORS

P-N-P transistors in miniature plastic envelopes intended for use in amplifier and switching applications. Complementary types are BST39/40.

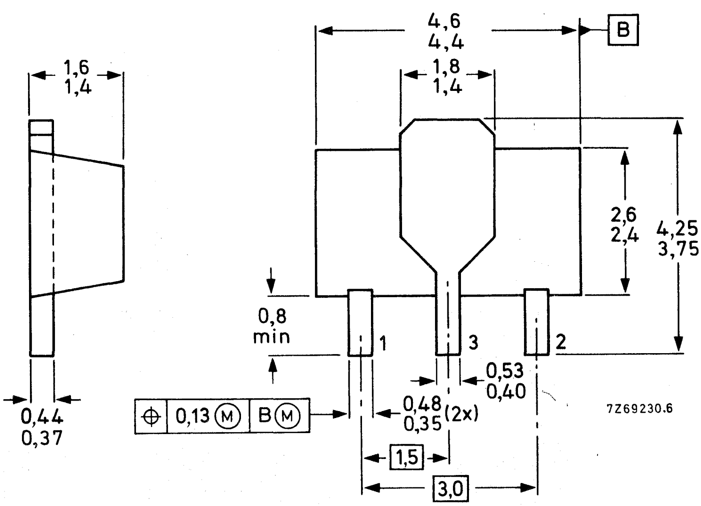
QUICK REFERENCE DATA

			BST15	BST16	
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	200	350	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	200	300	V
Collector current (d.c.)	$-I_C$	max.	1		A
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	1		W
Junction temperature	T_j	max.	150		°C
D.C. current gain $-V_{CE}$ = 10 V; $-I_C$ = 50 mA	h_{FE}		30 to 150	30 to 120	
Transition frequency $-V_{CE}$ = 10 V; $-I_C$ = 10 mA	f_T	>	15		MHz

MECHANICAL DATA

Dimensions in mm

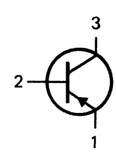
Fig. 1 SOT-89.



BOTTOM VIEW

Marking:

BST15 = BT1
BST16 = BT2



See also *Soldering Recommendations*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BST15	BST16	
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	200	350	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	200	300	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	4	6	V
Collector current (d.c.)	$-I_C$	max.	1		A
Base current	$-I_B$	max.	0,5		A
Total power dissipation up to T_{amb} = 25 °C*	P_{tot}	max.	1		W
Junction temperature	T_j	max.	150		°C
Storage temperature	T_{stg}		−65 to 150		°C

THERMAL RESISTANCE

from junction to ambient*	$R_{th\ j\text{-}mb}$	=	125	K/W
from junction to collector tab	$R_{th\ j\text{-}tab}$	=	10	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BST15	BST16	
Collector cut-off current					
$I_E = 0$; $-V_{CB} = 175$ V	$-I_{CBO}$	<	1	–	μA
$I_E = 0$; $-V_{CB} = 280$ V	$-I_{CBO}$	<	–	1	μA
$I_B = 0$; $-V_{CE} = 150$ V	$-I_{CEO}$	<	50	–	μA
$I_B = 0$; $-V_{CE} = 250$ V	$-I_{CEO}$	<	–	50	μA
Emitter cut-off current					
$I_C = 0$; $-V_{EB} = 4$ V	$-I_{EBO}$	<	20	–	μA
$I_C = 0$; $-V_{EB} = 6$ V	$-I_{EBO}$	<	–	20	μA
Collector-emitter breakdown voltage					
$I_B = 0$; $-I_C = 50$ mA; L = 25 mH	$-V_{(BR)CEO}$	>	200	300	V
Collector-emitter saturation voltage					
$-I_C = 50$ mA; $-I_B = 5$ mA	$-V_{CEsat}$	<	2,5	2,0	V
D.C. current gain					
$-V_{CE} = 10$ V; $-I_C = 50$ mA	h_{FE}		30 to 150	30 to 120	
Transition frequency at f = 30 MHz					
$-I_C = 10$ mA; $-V_{CE} = 10$ V	f_T	>	15		MHz
Collector capacitance at f = 1 MHz					
$I_E = I_e = 0$; $-V_{CB} = 10$ V	C_c	<	15		pF

* Mounted on an area of 2,5 cm^2 of a ceramic substrate; thickness 0,7 mm.

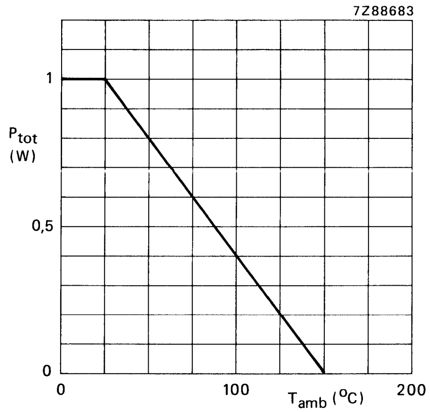


Fig. 2 Power derating curve.

SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N transistors in miniature plastic envelopes intended for use in amplifier and switching applications. Complementary p-n-p types are BST15/16.

QUICK REFERENCE DATA

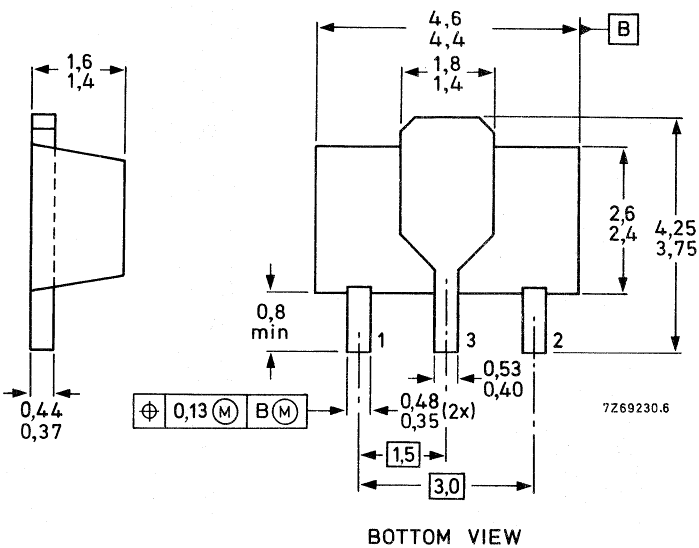
			BST39	BST40	
Collector-base voltage (open emitter)	V_{CBO}	max.	400	300	V
Collector-emitter voltage (open base)	V_{CEO}	max.	350	250	V
Collector current (d.c.)	I_C	max.	1		A
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	1		W
Junction temperature	T_j	max.	150		°C
D.C. current gain V_{CE} = 10 V; I_C = 20 mA	h_{FE}	min.	40		
Transition frequency at f = 5 MHz V_{CE} = 10 V; I_C = 10 mA	f_T	min.	70		MHz

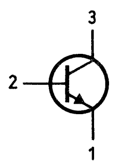
MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-89.

Marking
BST39 = AT1
BST40 = AT2





See also *Soldering Recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BST39	BST40	
Collector-base voltage (open emitter)	V_{CBO}	max.	400	300	V
Collector-emitter voltage (open base)	V_{CEO}	max.	350	250	V
Emitter-base voltage (open collector)	V_{EBO}	max.	5		V
Collector current (d.c.)	I_C	max.	1		A
Base current	I_B	max.	0,5		A
Total power dissipation up to T_{amb} = 25 °C*	P_{tot}	max.	1		W
Junction temperature	T_j	max.	150		°C
Storage temperature	T_{stg}		−65 to 150		°C

THERMAL RESISTANCE

from junction to ambient*	$R_{th\,j\text{-}a}$	=	125	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current $I_B = 0$; $V_{CE} = 300$ V	I_{CBO}	$\leqslant$	20	nA
Emitter cut-off current $I_C = 0$; $V_{EB} = 5$ V	I_{EBO}	$\leqslant$	10	μA
Collector-emitter saturation voltage $I_C = 50$ mA; $I_B = 4$ mA	V_{CEsat}	$\leqslant$	0,5	V
Base-emitter saturation voltage $I_C = 50$ mA; $I_B = 4$ mA	V_{BEsat}	$\leqslant$	1,3	V
D.C. current gain $V_{CE} = 10$ V; $I_C = 20$ mA	h_{FE}	$\leqslant$	40	
Collector capacitance at f = 1 MHz $I_E = i_e = 0$; $V_{CB} = 10$ V	C_c	$\leqslant$	2	pF
Emitter capacitance at f = 1 MHz $I_C = I_c = 0$; $V_{EB} = 5$ V	C_e	$\leqslant$	20	pF
Transition frequency at f = 5 MHz $V_{CE} = 10$ V; $I_C = 10$ mA	f_T	$\geqslant$	70	MHz

* Mounted on an area of 2,5 cm^2 of a ceramic substrate; thickness 0,7 mm.

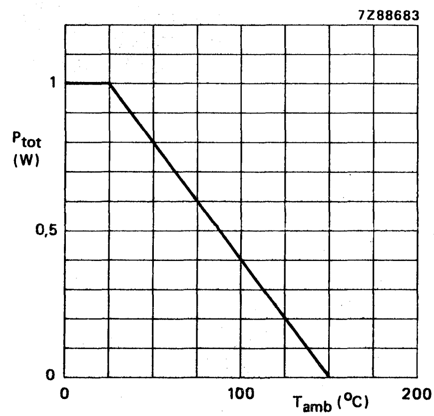


Fig. 2 Power derating curve.

N-P-N SILICON PLANAR DARLINGTON TRANSISTORS

Silicon n-p-n planar Darlington transistors for industrial switching applications, e.g. print hammer, solenoid, relay and lamp driving. Encapsulated in a microminiature SOT-89 envelope.

P-N-P complements are BST60, 61, 62 respectively.

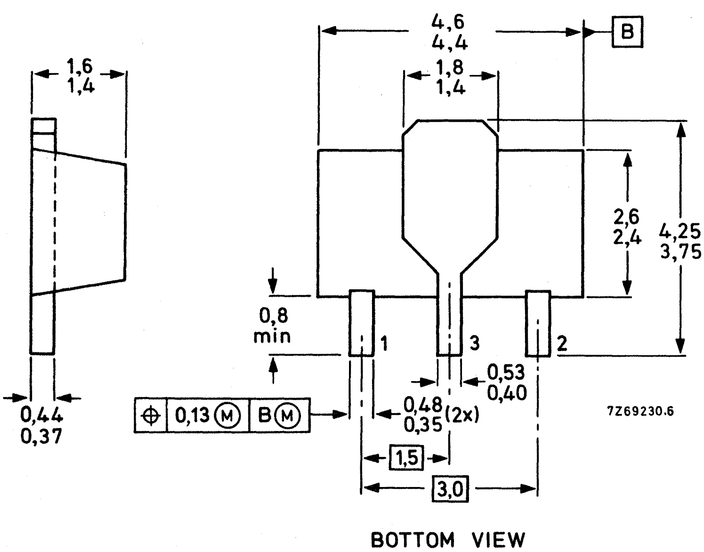
QUICK REFERENCE DATA

			BST50	BST51	BST52	
Collector-base voltage (open emitter)	V_{CBO}	max.	60	80	90	V
Collector-emitter voltage	V_{CER}	max.	45	60	80	V
Collector current	I_C	max.	0,5	0,5	0,5	A
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.		1		W
D.C. current gain I_C = 500 mA; V_{CE} = 10 V	h_{FE}	>		2000		
Collector-emitter saturation voltage I_C = 500 mA; I_B = 0,5 mA	V_{CEsat}	<		1,3		V
Turn-off time I_C = 500 mA; $I_{Bon} = -I_{Boff}$ = 0,5 mA	t_{off}	typ.		1500		ns

MECHANICAL DATA

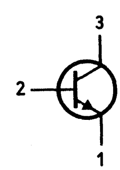
Dimensions in mm

Fig. 1 SOT-89.



Mark

BST50 = AS1
BST51 = AS2
BST52 = AS3



See also *Soldering recommendations*.

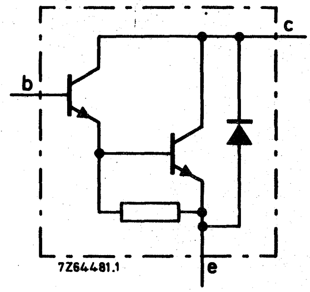


Fig. 2 Circuit diagram.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BST50	BST51	BST52	
Collector-base voltage (open emitter)	V_{CBO}	max.	60	80	90	V
Collector-emitter voltage*	V_{CER}	max.	45	60	80	V
Emitter-base voltage (open collector)	V_{EBO}	max.		5		V
Collector current (d.c.)	I_C	max.		0,5		A
Collector current (peak)	I_{CM}	max.		1,5		A
Base current (d.c.)	I_B	max.		0,1		A
Total power dissipation▲ up to T_{amb} = 25 °C	P_{tot}	max.		1		W
Storage temperature	T_{stg}			−65 to + 150		°C
Junction temperature**	T_j	max.		150		°C

THERMAL RESISTANCE**

From junction to ambient▲	$R_{th\,j\text{-}a}$	=	125	K/W
From junction to tab	$R_{th\,j\text{-}tab}$	=	10	K/W

* External R_{BE} not to exceed value shown in Fig. 5.

** Based on maximum average junction temperature in line with common industrial practice. The resulting higher junction temperature of the output transistor part is taken into account.

▲ Device mounted on a ceramic substrate; area = 2,5 cm², thickness = 0,7 mm.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current			
$V_{BE} = 0$; $V_{CE} = V_{CER}max$	I_{CES}	<	10 μA
Emitter cut-off current			
$I_C = 0$; $V_{EB} = 4$ V	I_{EBO}	<	10 μA
D.C. current gain*			
$I_C = 150$ mA; $V_{CE} = 10$ V	h_{FE}	>	1000
$I_C = 500$ mA; $V_{CE} = 10$ V	h_{FE}	>	2000
Collector-emitter saturation voltage			
$I_C = 500$ mA; $I_B = 0,5$ mA	V_{CEsat}	<	1,3 V
$I_C = 500$ mA; $I_B = 0,5$ mA; $T_j = 150$ °C	V_{CEsat}	<	1,3 V
Base-emitter saturation voltage			
$I_C = 500$ mA; $I_B = 0,5$ mA	V_{BEsat}	<	1,9 V
Switching times (see also Fig. 3 and Fig. 4)			
$I_C = 500$ mA; $I_{Bon} = -I_{Boff} = 0,5$ mA			
Turn-on time	t_{on}	typ.	400 ns
Turn-off time	t_{off}	typ.	1500 ns

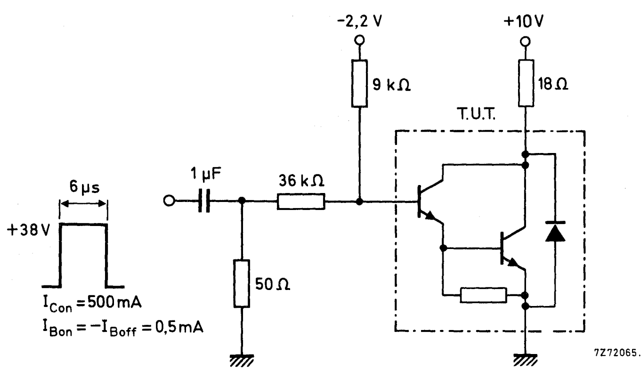


Fig. 3 Switching times test circuit.

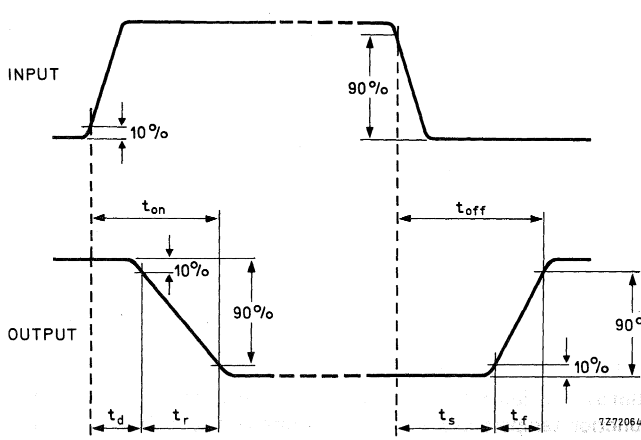


Fig. 4 Switching times waveform.

* Measured under pulsed conditions.

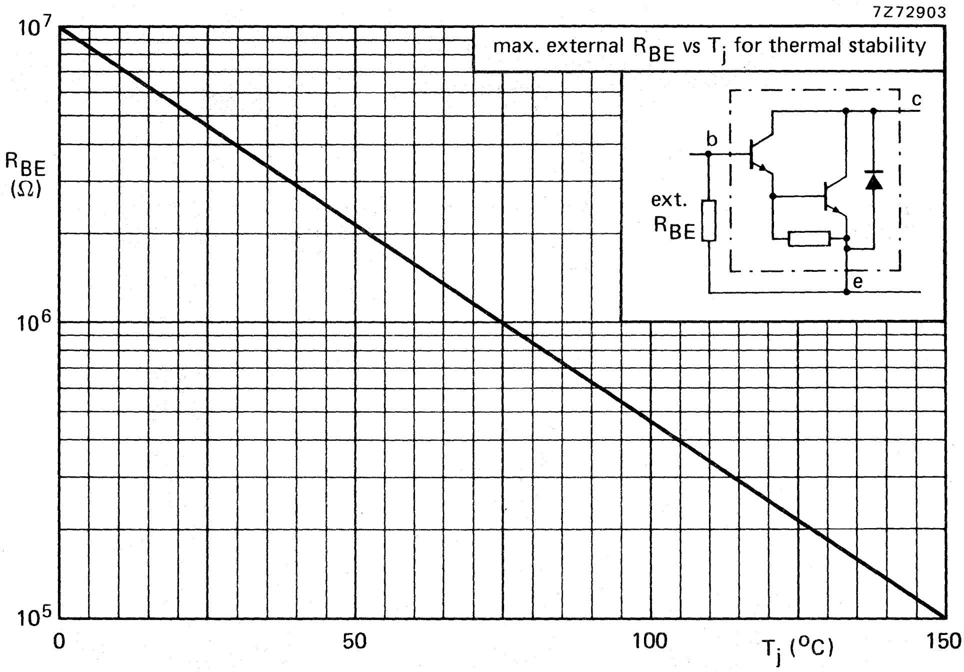


Fig. 5 Maximum values external R_{BE} as a function of junction temperature.

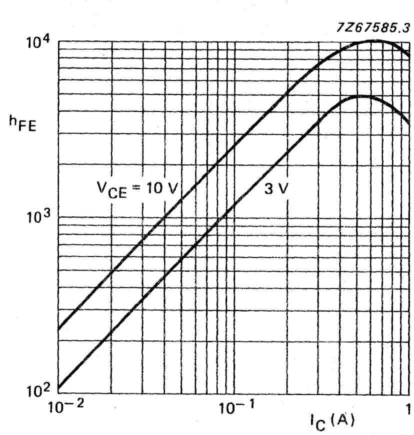


Fig. 6 T_j = 25 °C.

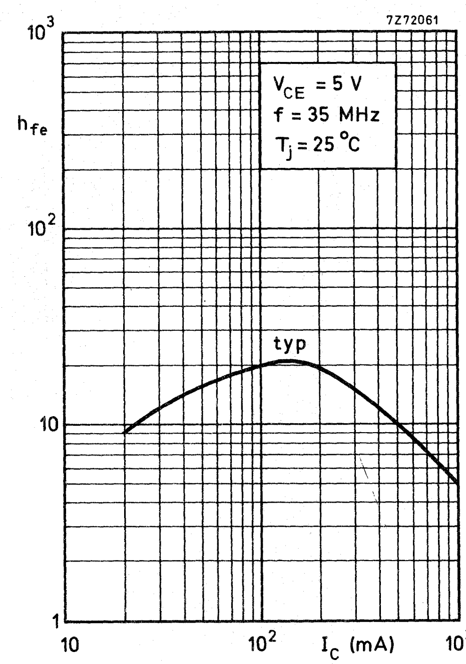


Fig. 7.

P-N-P SILICON PLANAR DARLINGTON TRANSISTORS

Silicon p-n-p planar Darlington transistors for industrial switching applications, e.g. print hammer, solenoid, relay and lamp driving. Encapsulated in a microminiature plastic SOT-89 envelope.

N-P-N complements are BST50, BST51 and BST52 respectively.

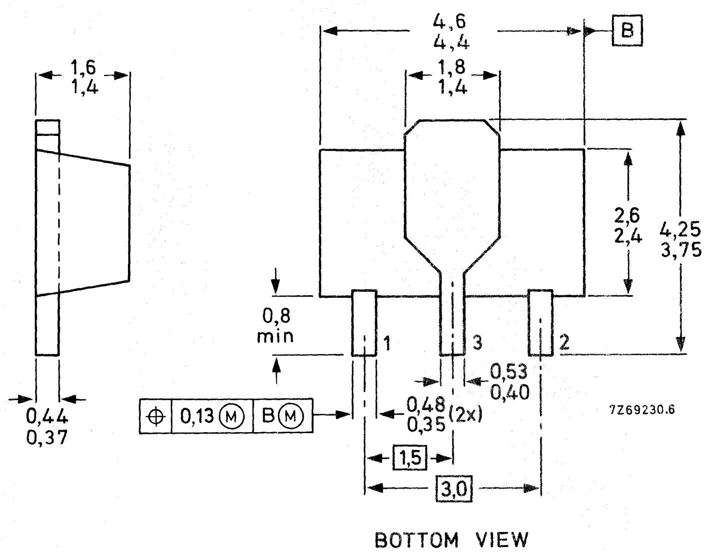
QUICK REFERENCE DATA

			BST60	BST61	BST62	
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	60	80	90	V
Collector-emitter voltage	$-V_{CER}$	max.	45	60	80	V
Collector current	$-I_C$	max.	0,5	0,5	0,5	A
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.		1		W
D.C. current gain $-I_C$ = 500 mA; $-V_{CE}$ = 10 V	h_{FE}	>		2000		
Collector-emitter saturation voltage $-I_C$ = 0,5 A; $-I_B$ = 0,5 mA	$-V_{CEsat}$	<		1,3		V
Turn-off time $-I_C$ = 500 mA; $-I_{Bon}$ = I_{Boff} = 0,5 mA	t_{off}	typ.		1500		ns

MECHANICAL DATA

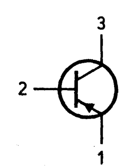
Dimensions in mm

Fig. 1 SOT-89.



Mark

BST60 = BS1
BST61 = BS2
BST62 = BS3



See also *Soldering recommendations.*

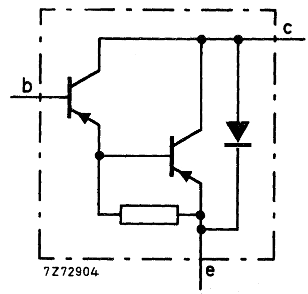


Fig. 2 Circuit diagram.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BST60	BST61	BST62	
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	60	80	90	V
Collector-emitter voltage*	$-V_{CER}$	max.	45	60	80	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.		5		V
Collector current (d.c.)	$-I_C$	max.		0,5		A
Collector current (peak)	$-I_{CM}$	max.		1,5		A
Base current (d.c.)	$-I_B$	max.		0,1		A
Total power dissipation▲ up to T_{amb} = 25 °C	P_{tot}	max.		1		W
Storage temperature	T_{stg}			−65 to + 150		°C
Junction temperature**	T_j	max.		150		°C

THERMAL RESISTANCE**

From junction to ambient▲	$R_{th\ j\text{-}a}$	=	125	K/W
From junction to tab	$R_{th\ j\text{-}tab}$	=	10	K/W

* External R_{BE} not to exceed value shown in Fig. 5.
** Based on maximum average junction temperature in line with common industrial practice. The resulting higher junction temperature of the output transistor part is taken into account.
▲ Device mounted on a ceramic substrate area 2,5 cm^2, thickness = 0,7 mm.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Collector cut-off current				
$V_{BE} = 0$; $-V_{CE} = -V_{CER}max$	$-I_{CES}$	<	10	μA
Emitter cut-off current				
$I_C = 0$; $V_{EB} = 4$ V	$-I_{EBO}$	<	10	μA
D.C. current gain*				
$-I_C = 150$ mA; $-V_{CE} = 10$ V	h_{FE}	>	1000	
$-I_C = 500$ mA; $-V_{CE} = 10$ V	h_{FE}	>	2000	
Collector-emitter saturation voltage				
$-I_C = 500$ mA; $-I_B = 0{,}5$ mA	$-V_{CEsat}$	<	1,3	V
$-I_C = 500$ mA; $-I_B = 0{,}5$ mA; $T_j = 150$ °C	$-V_{CEsat}$	<	1,3	V
Base-emitter saturation voltage				
$-I_C = 500$ mA; $-I_B = 0{,}5$ mA	$-V_{BEsat}$	<	1,9	V
Switching times (see also Fig. 3 and Fig. 4)				
$-I_C = 500$ mA; $-I_{Bon} = -I_{Boff} = 0{,}5$ mA				
Turn-on time	t_{on}	typ.	400	ns
Turn-off time	t_{off}	typ.	1500	ns

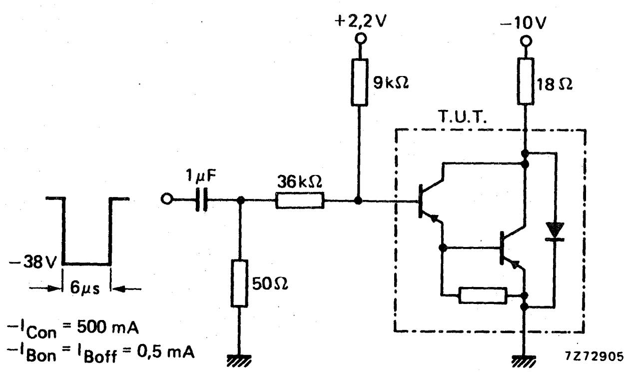


Fig. 3 Switching times test circuit.

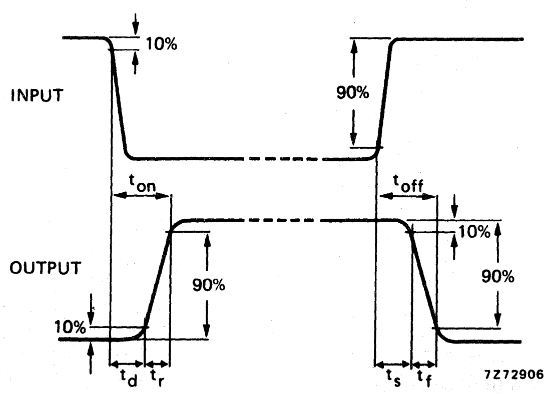


Fig. 4 Switching times waveform.

* Measured under pulsed conditions.

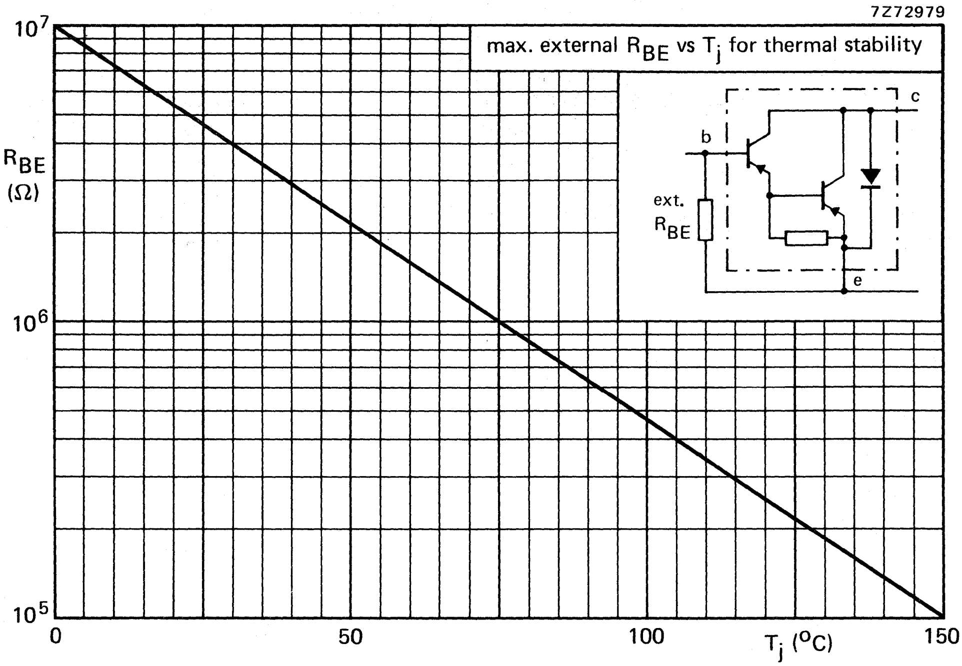


Fig. 5 Maximum values external R_{BE} as a function of junction temperature.

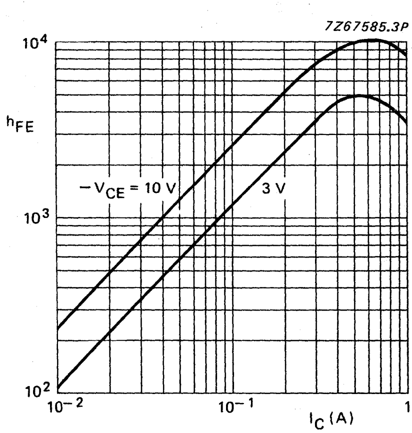


Fig. 6 T_j = 25 °C.

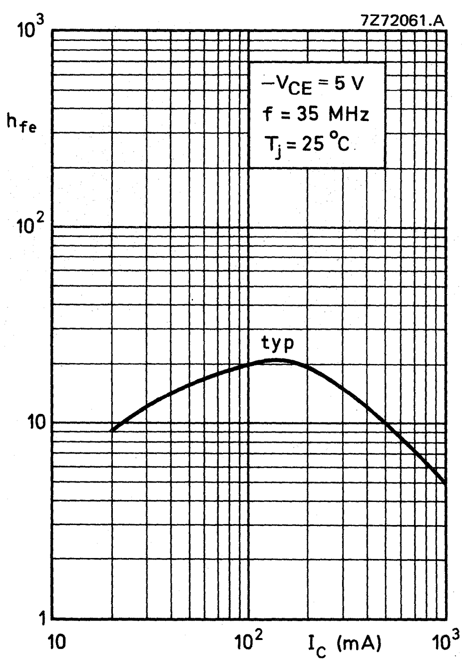


Fig. 7.

N-CHANNEL VERTICAL D-MOS TRANSISTOR

N-channel enhancement mode vertical D-MOS transistor in SOT-89 envelope and designed for use as Surface Mounted Device (SMD) in thin and thick-film circuits for application with relay, high-speed and line-transformer drivers.

Features

- Very low R_{DSon}
- Direct interface to C-MOS, TTL, etc.
- High-speed switching
- No second breakdown

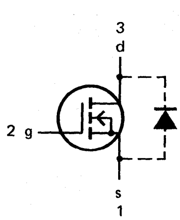
QUICK REFERENCE DATA

Drain-source voltage	V_{DS}	max.	80	V
Gate-source voltage (open drain)	V_{GSO}	max.	20	V
Drain current (d.c.)	I_D	max.	0,5	A
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	1	W
Drain-source ON-resistance I_D = 500 mA; V_{GS} = 10 V	R_{DSon}	typ. <	2,0 4,0	Ω Ω
Transfer admittance I_D = 500 mA; V_{DS} = 15 V; f = 1 kHz	$\lvert y_{fs} \rvert$	typ.	300	mS

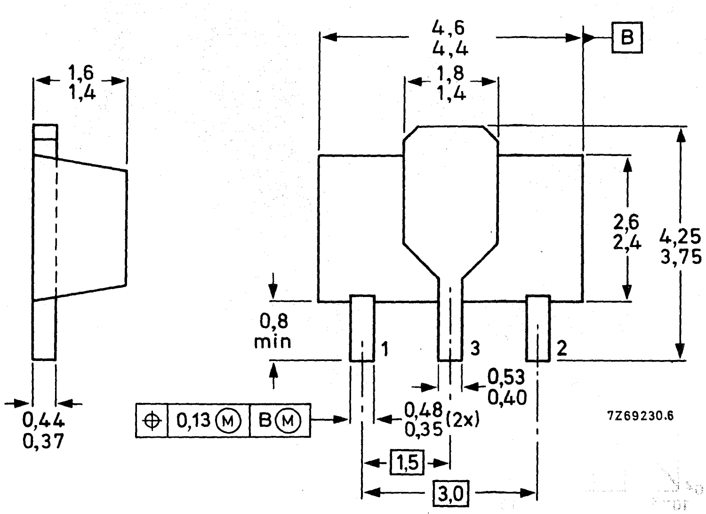
MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-89.



Marking: KM



BOTTOM VIEW

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	V_{DS}	max.	80	V
Gate-source voltage (open drain)	V_{GSO}	max.	20	V
Drain current (d.c.)	I_D	max.	0,5	A
Drain current (peak)	I_{DM}	max.	1,0	A
Total power dissipation up to T_{amb} = 25 °C*	P_{tot}	max.	1	W
Storage temperature	T_{stg}	−65 to + 150		°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j\text{-}a}$		125	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Drain-source breakdown voltage I_D = 100 μA; V_{GS} = 0	$V_{(BR)DS}$	>	80	V
Drain-source leakage current V_{DS} = 60 V; V_{GS} = 0	I_{DSS}	<	10	μA
Gate-source leakage current V_{GS} = 20 V; V_{DS} = 0	I_{GSS}	<	100	nA
Gate threshold voltage I_D = 1 mA; V_{DS} = V_{GS}	$V_{GS(th)}$	> <	1,5 3,5	V V
Drain-source ON-resistance I_D = 500 mA; V_{GS} = 10 V	R_{DSon}	typ. <	2,0 4,0	Ω Ω
Transfer admittance at f = 1 kHz I_D = 500 mA; V_{DS} = 15 V	$\|y_{fs}\|$	typ.	300	mS
Input capacitance at f = 1 MHz V_{DS} = 10 V; V_{GS} = 0	C_{is}	typ.	45	pF
Output capacitance at f = 1 MHz V_{DS} = 10 V; V_{GS} = 0	C_{os}	typ.	30	pF
Feedback capacitance at f = 1 MHz V_{DS} = 10 V; V_{GS} = 0	C_{rs}	typ.	8	pF
Switching times (see Figs 2 and 3) I_D = 500 mA; V_{DS} = 50 V; V_{GS} = 0 to 10 V	t_{on} t_{off}	< <	10 15	ns ns

* Transistors mounted on a substrate with surface area of 2,5 cm^2 and thickness of 0,7 mm.

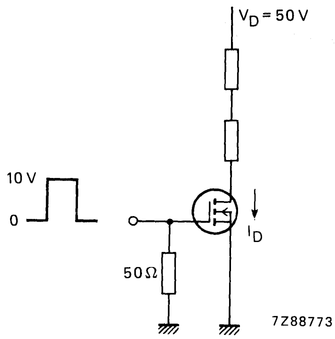


Fig. 2 Switching times test circuit.

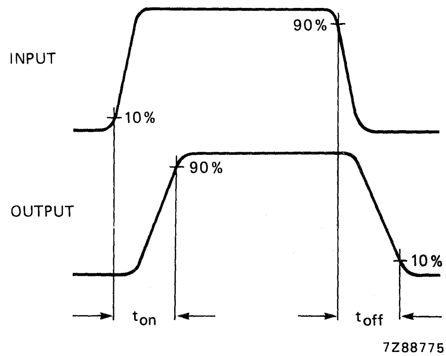


Fig. 3 Input and output waveforms.

N-CHANNEL VERTICAL D-MOS TRANSISTOR

N-channel enhancement mode vertical D-MOS transistor in SOT-23 envelope and designed for use as Surface Mounted Device (SMD) in thin and thick-film circuits for telephone ringer and for application with relay, high-speed and line transformer drivers.

Features

- Direct interface to C-MOS, TTL, etc.
- High-speed switching
- No second breakdown

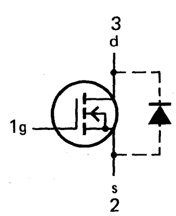
QUICK REFERENCE DATA

Drain-source voltage	V_{DS}	max.	80	V
Drain-source voltage (non-repetitive peak; $t_p \leqslant 2$ ms)	$V_{DS(SM)}$	max.	100	V
Gate-source voltage (open drain)	V_{GSO}	max.	20	V
Drain current (d.c.)	I_D	max.	175	mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300	mW
Drain-source ON-resistance I_D = 150 mA; V_{GS} = 5 V	R_{DSon}	typ. <	7 10	Ω Ω
Transfer admittance I_D = 175 mA; V_{DS} = 5 V; f = 1 kHz	$\|y_{fs}\|$	typ.	150	mS

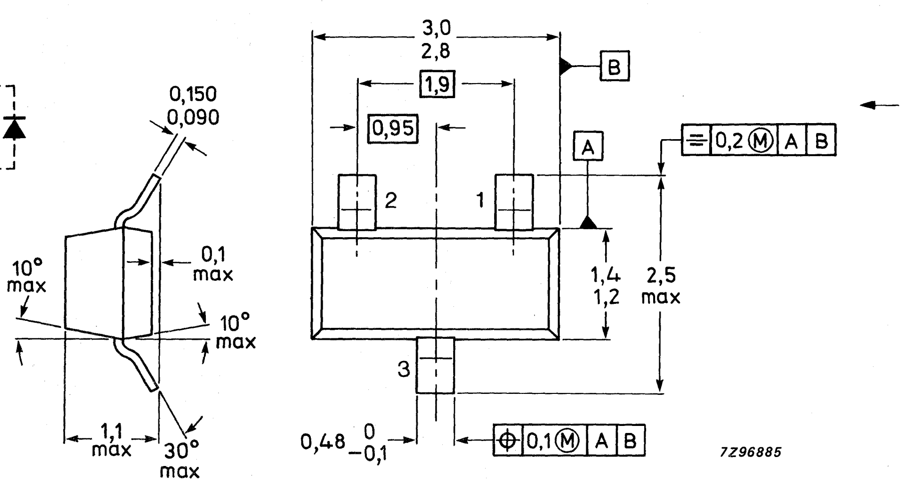
MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-23.



Marking: 02



TOP VIEW

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	V_{DS}	max.	80	V
Drain-source voltage (non-repetitive peak; $t_p \leq 2$ ms)	$V_{DS(SM)}$	max.	100	V
Gate-source voltage (open drain)	V_{GSO}	max.	20	V
Drain surrent (d.c.)	I_D	max.	175	mA
Drain current (peak)	I_{DM}	max.	600	mA
Total power dissipation up to T_{amb} = 25 °C*	P_{tot}	max.	300	mW
Storage temperature range	T_{stg}	−65 to + 150		°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j\text{-}a}$	=	430	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Drain-source breakdown voltage I_D = 100 μA; V_{GS} = 0	$V_{(BR)DS}$	>	80	V
Drain-source leakage current V_{DS} = 60 V; V_{GS} = 0	I_{DSS}	<	1,0	μA
Gate-source leakage current V_{GS} = 20 V; V_{DS} = 0	I_{GSS}	<	100	nA
Gate-source cut-off voltage I_D = 1 mA; V_{DS} = V_{GS}	$V_{(P)GS}$	> <	1,5 3,5	V V
Drain-source ON-resistance I_D = 150 mA; V_{GS} = 5 V	R_{DSon}	typ. <	7 10	Ω Ω
Transfer admittance at f = 1 kHz I_D = 175 mA; V_{DS} = 5 V	$\|y_{fs}\|$	typ.	150	mS
Input capacitance at f = 1 MHz V_{DS} = 10 V; V_{GS} = 0	C_{is}	typ.	15	pF
Output capacitance at f = 1 MHz V_{DS} = 10 V; V_{GS} = 0	C_{os}	typ.	13	pF
Feedback capacitance at f = 1 MHz V_{DS} = 10 V; V_{GS} = 0	C_{rs}	typ.	3	pF
Switching times (see Figs 2 and 3) I_D = 175 mA; V_{DS} = 50 V; V_{GS} = 0 to 10 V	t_{on}	typ. <	4 10	ns ns
	t_{off}	typ. <	4 10	ns ns

* Transistors mounted on a ceramic substrate of 7 mm x 5 mm x 0,7 mm.

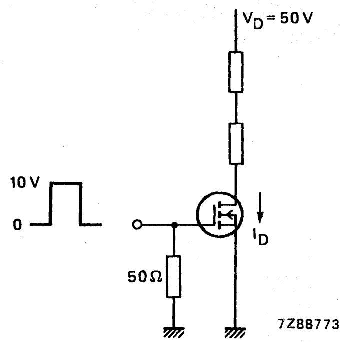


Fig. 2 Switching times test circuit.

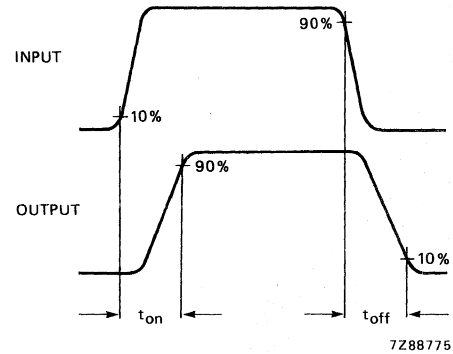


Fig. 3 Input and output waveforms.

N-CHANNEL VERTICAL D-MOS TRANSISTOR

N-channel vertical D-MOS transistor in SOT-89 envelope and designed for use as line current interrupter in telephone sets and for application in relay, high-speed and line-transformer drivers.

Features

- Direct interface to C-MOS, TTL, etc.
- High-speed switching
- No second breakdown

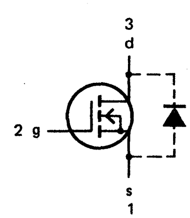
QUICK REFERENCE DATA

Drain-source voltage	V_{DS}	max.	200	V
Gate-source voltage (open drain)	V_{GSO}	max.	20	V
Drain current (d.c.)	I_D	max.	250	mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	1	W
Drain-source ON-resistance I_D = 250 mA; V_{GS} = 10 V	R_{DSon}	typ. <	6 12	Ω Ω
Transfer admittance I_D = 250 mA; V_{DS} = 15 V; f = 1 kHz	$\lvert y_{fs} \rvert$	typ.	250	mS

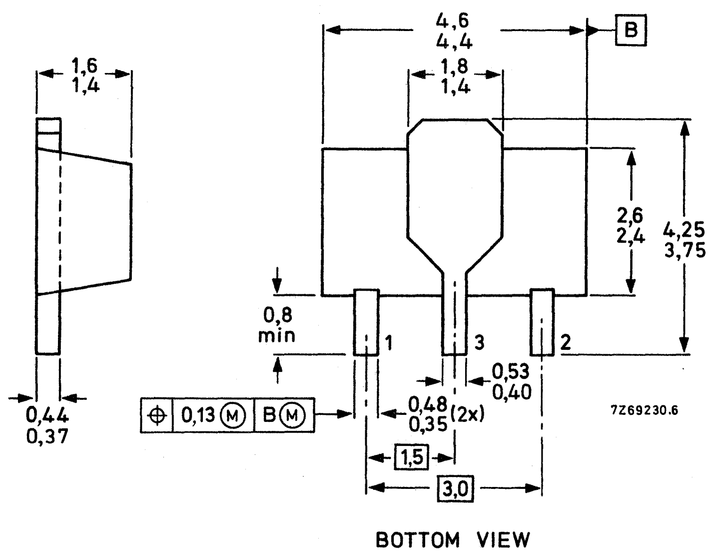
MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-89.



Marking: KN



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	V_{DS}	max.	200 V
Gate-source voltage (open drain)	V_{GSO}	max.	20 V
Drain current (d.c.)	I_D	max.	250 mA
Drain current (peak)	I_{DM}	max.	800 mA
Total power dissipation up to T_{amb} = 25 °C*	P_{tot}	max.	1 W
Storage temperature	T_{stg}	−65 to + 150 °C	
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE

From junction to ambient	$R_{th\ j\text{-}a}$	=	125 K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Drain-source breakdown voltage I_D = 100 μA; V_{GS} = 0	$V_{(BR)DS}$	>	200 V
Drain-source leakage current V_{DS} = 160 V; V_{GS} = 0	I_{DSS}	<	10 μA
Gate-source leakage current V_{GS} = 20 V; V_{DS} = 0	I_{GSS}	<	100 nA
Gate threshold voltage I_D = 1 mA; V_{DS} = V_{GS}	$V_{GS(th)}$	> <	0,8 V 2,8 V
Drain-source ON-resistance I_D = 250 mA; V_{GS} = 10 V	R_{DSon}	typ. <	6 Ω 12 Ω
Transfer admittance at f = 1 kHz I_D = 250 mA; V_{DS} = 15 V	$\|y_{fs}\|$	typ.	250 mS
Input capacitance at f = 1 MHz V_{DS} = 10 V; V_{GS} = 0	C_{is}	typ.	70 pF
Output capacitance at f = 1 MHz V_{DS} = 10 V; V_{GS} = 0	C_{os}	typ.	20 pF
Feedback capacitance at f = 1 MHz V_{DS} = 10 V; V_{GS} = 0	C_{rs}	typ.	5 pF
Switching times (see Figs 2 and 3) I_D = 250 mA; V_{DS} = 50 V; V_{GS} = 0 to 10 V	t_{on}	typ. <	4 ns 10 ns
	t_{off}	typ. <	15 ns 25 ns

* Transistor mounted on a ceramic substrate with area of 2,5 cm^2 and thickness of 0,7 mm.

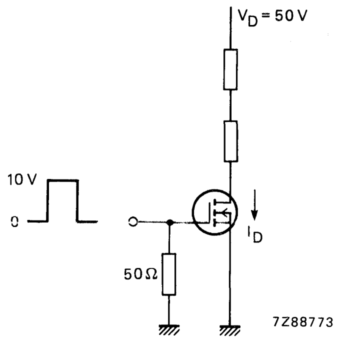


Fig. 2 Switching times test circuit.

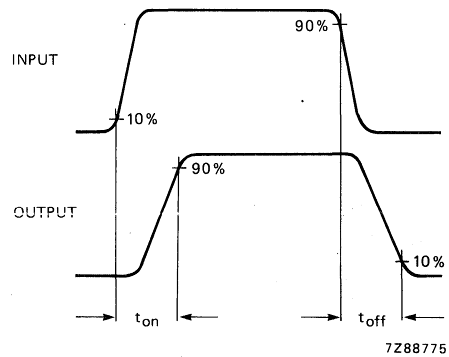


Fig. 3 Input and output waveforms.

N-CHANNEL VERTICAL D-MOS TRANSISTOR

N-channel enhancement mode vertical D-MOS transistor in SOT-89 envelope and designed for use as Surface Mounted Device (SMD) in thin and thick-film circuits for application with relay, high-speed and line-transformer drivers.

Features

- Direct interface to C-MOS, TTL, etc.
- High-speed switching
- No second breakdown

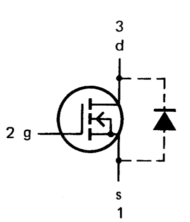
QUICK REFERENCE DATA

Drain-source voltage	V_{DS}	max.	180 V
Drain-source voltage (non-repetitive peak; $t_p \leq 2$ ms)	$V_{DS(SM)}$	max.	200 V
Gate-source voltage (open drain)	V_{GSO}	max.	20 V
Drain current (d.c.)	I_D	max.	300 mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	1 W
Drain-source ON-resistance I_D = 15 mA; V_{GS} = 3 V	R_{DSon}	typ.	7 Ω
		<	10 Ω
Transfer admittance I_D = 300 mA; V_{DS} = 15 V; f = 1 kHz	$\|y_{fs}\|$	typ.	250 mS

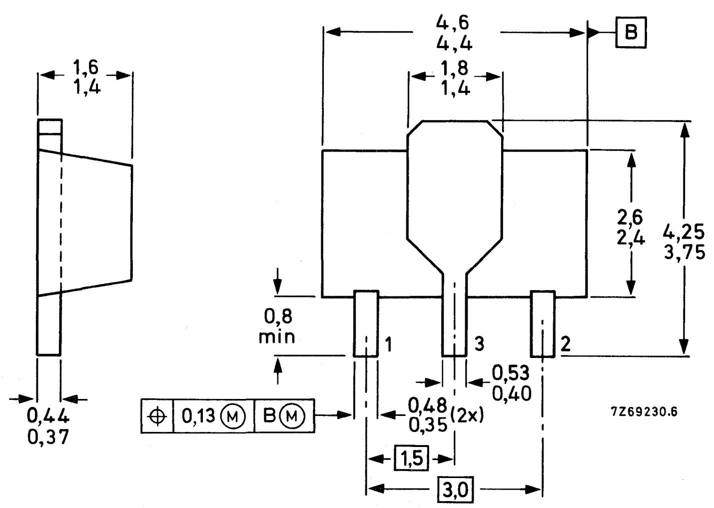
MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-89.



Marking: K0



BOTTOM VIEW

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	V_{DS}	max.	180	V
Drain-source voltage (non-repetitive peak; $t_p \leqslant 2$ ms)	$V_{DS(SM)}$	max.	200	V
Gate-source voltage (open drain)	V_{GSO}	max.	20	V
Drain current (d.c.)	I_D	max.	300	mA
Drain current (peak)	I_{DM}	max.	800	mA
Total power dissipation up to T_{amb} = 25 °C*	P_{tot}	max.	1	W
Storage temperature	T_{stg}	−65 to + 150		°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j\text{-}a}$	=	125	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Drain-source breakdown voltage $I_D = 100\ \mu A$; $V_{GS} = 0$	$V_{(BR)DS}$	>	180	V
Drain-source leakage current $V_{DS} = 120$ V; $V_{GS} = 0$	I_{DSS}	<	10	μA
Gate-source leakage current $V_{GS} = 20$ V; $V_{DS} = 0$	I_{GSS}	<	100	nA
Gate threshold voltage $I_D = 100\ \mu A$; $V_{DS} = V_{GS}$	$V_{GS(th)}$	> <	0,7 2,7	V V
Drain-source ON-resistance $I_D = 15$ mA; $V_{GS} = 3$ V	R_{DSon}	typ. <	7 10	Ω Ω
$I_D = 300$ mA; $V_{GS} = 10$ V	R_{DSon}	typ.	6	Ω
Transfer admittance at f = 1 kHz $I_D = 300$ mA; $V_{DS} = 15$ V	$\|y_{fs}\|$	typ.	250	mS
Input capacitance at f = 1 MHz $V_{DS} = 10$ V; $V_{GS} = 0$	C_{is}	typ.	50	pF
Output capacitance at f = 1 MHz $V_{DS} = 10$ V; $V_{GS} = 0$	C_{os}	typ.	20	pF
Feedback capacitance at f = 1 MHz $V_{DS} = 10$ V; $V_{GS} = 0$	C_{rs}	typ.	6	pF
Switching times (see Figs 2 and 3) $I_D = 300$ mA; $V_{DS} = 50$ V; $V_{GS} = 0$ to 10 V	t_{on} t_{off}	< <	10 15	ns ns

* Transistors mounted on a ceramic substrate with area of 2,5 cm^2 and thickness of 0,7 mm.

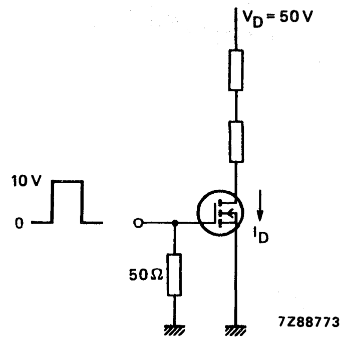


Fig. 2 Switching times test circuit.

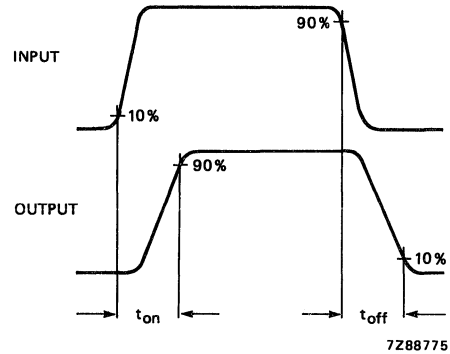


Fig. 3 Input and output waveforms.

P-CHANNEL VERTICAL D-MOS TRANSISTOR

P-channel vertical D-MOS transistor in SOT-89 envelope and intended for use in relay, high-speed and line-transformer drivers, using SMD technology.

Features

- Very low R_{DSon}
- Direct interface to C-MOS
- High-speed switching
- No second breakdown

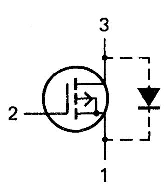
QUICK REFERENCE DATA

Drain-source voltage	$-V_{DS}$	max.	60	V
Gate-source voltage (open drain)	$-V_{GSO}$	max.	20	V
Drain current (d.c.)	$-I_D$	max.	0,3	A
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	1	W
Drain-source ON-resistance $-I_D$ = 200 mA; $-V_{GS}$ = 10 V	R_{DSon}	typ. max.	4,5 6	Ω Ω
Transfer admittance $-I_D$ = 200 mA; $-V_{DS}$ = 15 V; f = 1 kHz	$\lvert y_{fs} \rvert$	typ.	200	mS

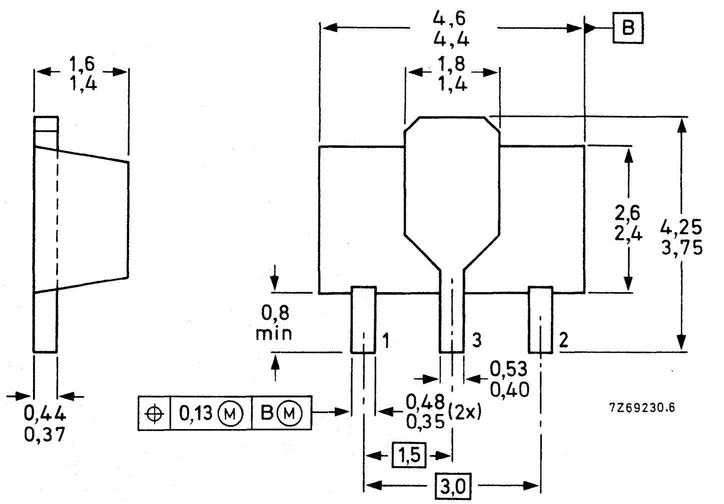
MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-89.



Marking: LM



BOTTOM VIEW

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	$-V_{DS}$	max.	60 V
Gate-source voltage (open drain)	$-V_{GSO}$	max.	20 V
Drain current (d.c.)	$-I_D$	max.	0,3 A
Drain current (peak)	$-I_{DM}$	max.	0,8 A
Total power dissipation up to T_{amb} = 25 °C*	P_{tot}	max.	1 W
Storage temperature	T_{stg}	−65 to +	150 °C
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j\text{-}a}$	=	125 K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Drain-source breakdown voltage $-I_D$ = 100 μA; $-V_{GS}$ = 0	$-V_{(BR)DS}$	>	60 V
Drain-source leakage current $-V_{DS}$ = 45 V; V_{GS} = 0	$-I_{DSS}$	<	10 μA
Gate-source leakage current $-V_{GS}$ = 20 V; V_{DS} = 0	$-I_{GSS}$	<	100 nA
Gate threshold voltage $-I_D$ = 1 mA; V_{DS} = V_{GS}	$-V_{GS(th)}$	> <	1,5 V 3,5 V
Drain-source ON-resistance $-I_D$ = 200 mA; $-V_{GS}$ = 10 V	R_{DSon}	typ. <	4,5 Ω 6 Ω
Transfer admittance at f = 1 kHz $-I_D$ = 200 mA; $-V_{DS}$ = 15 V	$\|y_{fs}\|$	typ.	200 mS
Input capacitance at f = 1 MHz $-V_{DS}$ = 10 V; V_{GS} = 0	C_{is}	typ.	55 pF
Output capacitance at f = 1 MHz $-V_{DS}$ = 10 V; V_{GS} = 0	C_{os}	typ.	30 pF
Feedback capacitance at f = 1 MHz $-V_{DS}$ = 10 V; V_{GS} = 0	C_{rs}	typ.	8 pF
Switching times (see Figs 2 and 3) $-I_D$ = 200 mA; $-V_{DS}$ = 50 V; $-V_{GS}$ = 0 to 10 V	t_{on} t_{off}	typ. typ.	4 ns 20 ns

* Transistor mounted on a ceramic substrate: area = 2,5 cm^2 and thickness = 0,7 mm.

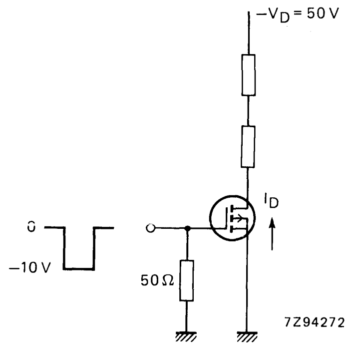


Fig. 2 Switching time test circuit.

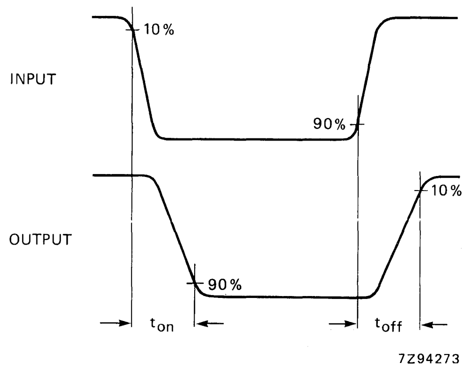


Fig. 3 Input and output waveforms.

P-CHANNEL VERTICAL D-MOS TRANSISTOR

P-channel vertical D-MOS transistor in SOT-89 envelope and intended for use in relay, high-speed and line-transformer drivers, using SMD-technology.

Features

- Very low R_{DSon}
- Direct interface to C-MOS, TTL
- High-speed switching
- No second breakdown

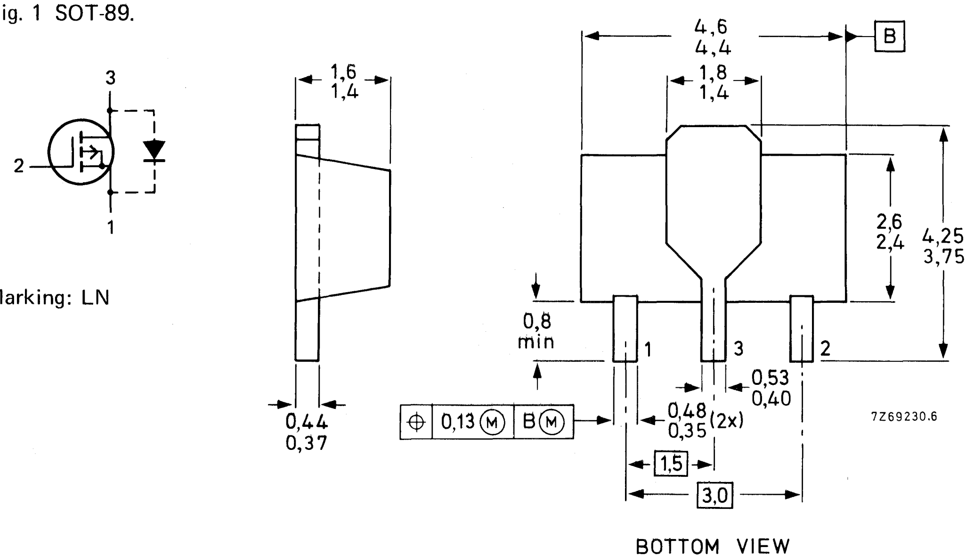
QUICK REFERENCE DATA

Drain-source voltage	$-V_{DS}$	max.	50	V
Gate-source voltage (open drain)	$-V_{GSO}$	max.	20	V
Drain current (d.c.)	$-I_D$	max.	0,25	A
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	1	W
Drain-source ON-resistance $-I_D$ = 200 mA; $-V_{GS}$ = 10 V	R_{DSon}	typ.	7,5	Ω
		max.	10	Ω
Transfer admittance $-I_D$ = 200 mA; $-V_{DS}$ = 15 V; f = 1 kHz	$\lvert y_{fs} \rvert$	typ.	125	mS

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-89.



Marking: LN

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage	$-V_{DS}$	max.	50	V
Gate-source voltage (open drain)	$-V_{GSO}$	max.	20	V
Drain current (d.c.)	$-I_D$	max.	0,25	A
Drain current (peak)	$-I_{DM}$	max.	0,5	A
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	1	W
Storage temperature	T_{stg}	−65 to + 150		°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j\text{-}a}$	=	125	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Drain-source breakdown voltage $-I_D$ = 100 μA; $-V_{GS}$ = 0	$-V_{(BR)DS}$	>	50	V
Drain-source leakage current $-V_{DS}$ = 1 V; V_{GS} = 0	$-I_{DSS}$	<	10	μA
Gate-source leakage current $-V_{GS}$ = 20 V; V_{DS} = 0	$-I_{GSS}$	<	100	nA
Gate threshold voltage $-I_D$ = 1 mA; V_{DS} = V_{GS}	$-V_{GS(th)}$	> <	1,5 3,5	V V
Drain-source ON-resistance $-I_D$ = 200 mA; $-V_{GS}$ = 10 V	R_{DSon}	typ. <	7,5 10	Ω Ω
Transfer admittance at f = 1 kHz $-I_D$ = 200 mA; $-V_{DS}$ = 15 V	$\|y_{fs}\|$	typ.	125	mS
Input capacitance at f = 1 MHz → $-V_{DS}$ = 10 V; V_{GS} = 0	C_{is}	typ.	30	pF
Output capacitance at f = 1 MHz → $-V_{DS}$ = 10 V; V_{GS} = 0	C_{os}	typ.	20	pF
Feedback capacitance at f = 1 MHz → $-V_{DS}$ = 10 V; V_{GS} = 0	C_{rs}	typ.	5	pF
Switching times (see Figs 2 and 3) → $-I_D$ = 200 mA; $-V_{DS}$ = 40 V; $-V_{GS}$ = 0 to 10 V	t_{on} t_{off}	typ. typ.	4 10	ns ns

* Transistor mounted on a ceramic substrate: area = 2,5 cm^2; thickness = 0,7 mm.

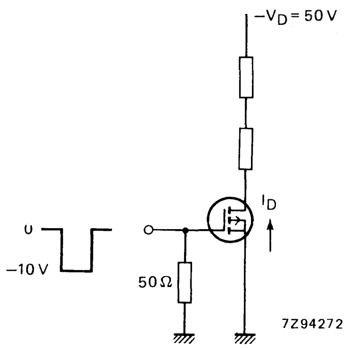


Fig. 2 Switching times test circuit.

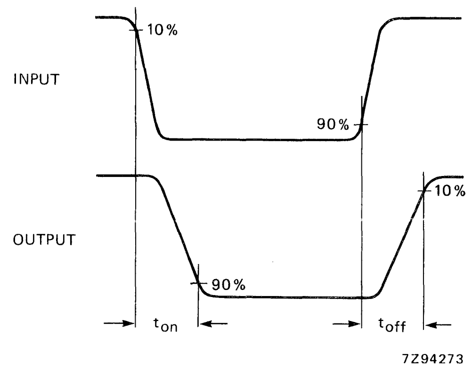


Fig. 3 Input and output waveforms.

SILICON PLANAR EPITAXIAL TRANSISTORS

- **High-speed switching**

N-P-N transistor in a microminiature plastic envelope. It is intended for very high-speed saturated switching in thick and thin-film circuits.

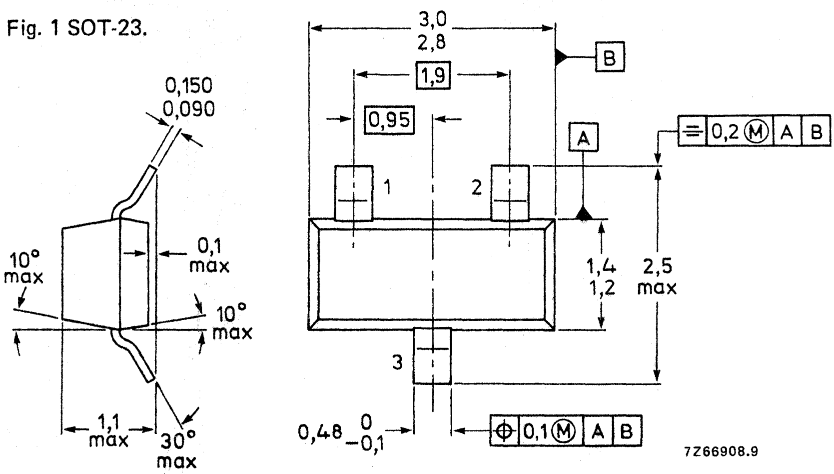
QUICK REFERENCE DATA

Collector-base voltage (open emitter)	V_{CBO}	max.	20	V
Collector-emitter voltage (V_{BE} = 0)	V_{CES}	max.	20	V
Collector-emitter voltage (open base)	V_{CEO}	max.	12	V
Collector current (peak value)	I_{CM}	max.	200	mA
Total power dissipation up to T_{amb} = 65 °C	P_{tot}	max.	250	mW
Junction temperature	T_j	max.	175	°C
D.C. current gain				
I_C = 10 mA; V_{CE} = 1 V	h_{FE}		40 to 120	
I_C = 50 mA; V_{CE} = 1 V	h_{FE}	>	25	
Transition frequency at f = 100 MHz		>	400	MHz
I_C = 10 mA; V_{CE} = 10 V	f_T	typ.	500	MHz
Storage time				
$I_C = I_B = -I_{BM}$ = 10 mA	t_s	<	13	ns

MECHANICAL DATA

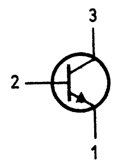
Dimensions in mm

Fig. 1 SOT-23.

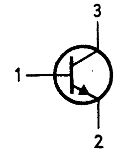


Marking code

BSV52 = B2



BSV52R = B4



R-types are available on request.

See also *Soldering recommendations.*

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter) See Fig. 4	V_{CBO}	max.	20	V
Collector-emitter voltage ($V_{BE} = 0$) See Fig. 4	V_{CES}	max.	20	V
Collector-emitter voltage (open base) $I_C = 10$ mA (see Fig. 4)	V_{CEO}	max.	12	V
Emitter-base voltage (open collector) See Fig. 4	V_{EBO}	max.	5	V
Collector current (d.c.)	I_C	max.	100	mA
Collector current (peak value)	I_{CM}	max.	200	mA
Total power dissipation up to $T_{amb} = 65\ ^oC$ **	P_{tot}	max.	250	mW
Storage temperature	T_{stg}	−65 to + 175		^oC
Junction temperature	T_j	max.	175	^oC

THERMAL CHARACTERISTICS*

$T_j = Px\ (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	60	K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280	K/W
From soldering points to ambient**	$R_{th\ s\text{-}a}$	=	90	K/W

CHARACTERISTICS

$T_j = 25\ ^oC$ unless otherwise specified

Collector cut-off current				
$I_E = 0$; $V_{CB} = 10$ V	I_{CBO}	<	100	nA
$I_E = 0$; $V_{CB} = 10$ V; $T_j = 125\ ^oC$	I_{CBO}	<	5	μA
Saturation voltages				
$I_C = 10$ mA; $I_B = 300$ μA	V_{CEsat}	<	300	mV
$I_C = 10$ mA; $I_B = 1$ mA	V_{CEsat}	<	250	mV
	V_{BEsat}		700 to 850	mV
$I_C = 50$ mA; $I_B = 5$ mA	V_{CEsat}	<	400	mV
	V_{BEsat}	<	1200	mV
D.C. current gain				
$I_C = 1$ mA; $V_{CE} = 1$ V	h_{FE}	>	25	
$I_C = 10$ mA; $V_{CE} = 1$ V	h_{FE}		40 to 120	
$I_C = 50$ mA; $V_{CE} = 1$ V	h_{FE}	>	25	
Transition frequency at f = 100 MHz				
$I_C = 10$ mA; $V_{CE} = 10$ V	f_T	>	400	MHz
		typ.	500	MHz

* See *Thermal characteristics.*

** Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

Collector capacitance at f = 1 MHz $I_E = I_e = 0$; $V_{CB} = 5$ V	C_c	<	4 pF
Emitter capacitance at f = 1 MHz $I_C = I_c = 0$; $V_{EB} = 1$ V	C_e	<	4,5 pF
Switching times Storage time $I_C = I_B = -I_{BM} = 10$ mA	t_s	<	13 ns
Turn on time when switched from $-V_{BE} = 1{,}5$ V to $I_C = 10$ mA; $I_B = 3$ mA	t_{on}	<	12 ns
Turn off time when switched from $I_C = 10$ mA; $I_B = 3$ mA to cut-off with $-I_{BM} = 1{,}5$ mA	t_{off}	<	18 ns

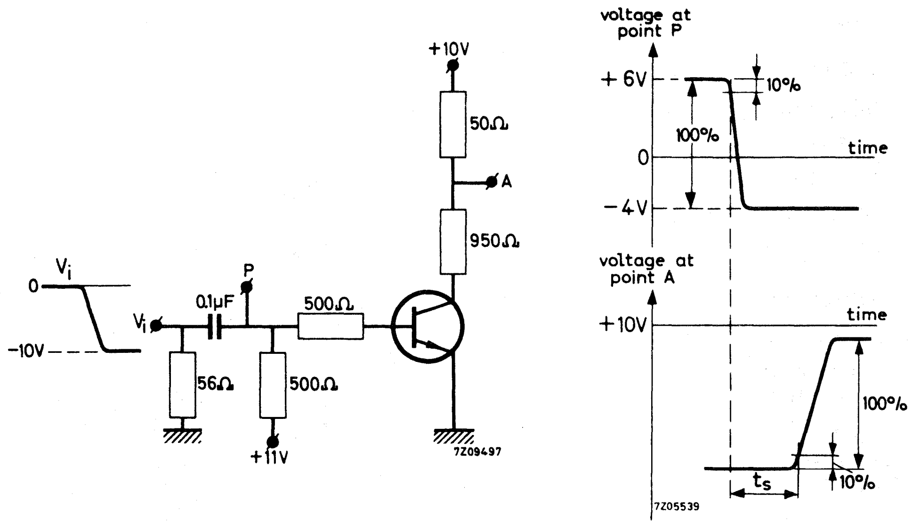


Fig. 2 Test circuit and waveform storage time.

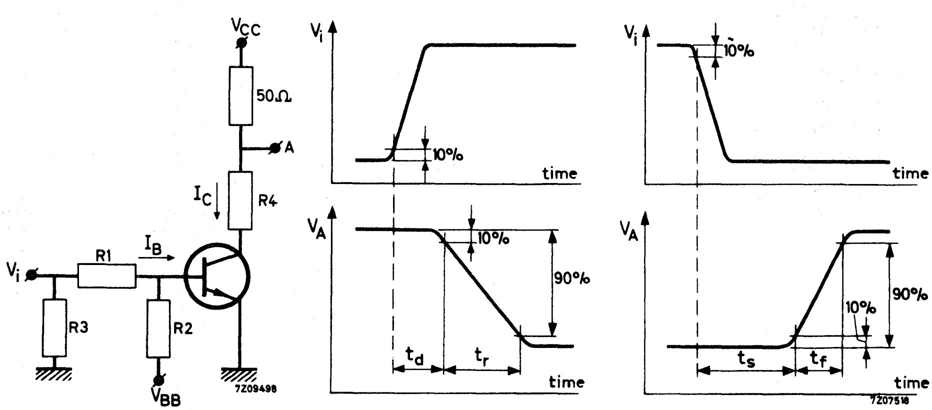


Fig. 3 Test circuit and waveforms turn on and turn off time.

Pulse generator:				Oscilloscope:			
Rise time	t_r	<	1 ns	Input impedance	R_i	=	50 Ω
Pulse duration	t	>	300 ns	Rise time	t_r	<	1 ns
Duty cycle	δ	<	0,02				
Source impedance	R_S	=	50 Ω				

							turn on time			turn off time	
I_C mA	I_B mA	$-I_{BM}$ mA	V_{CC} V	R_1; R_2 kΩ	R_3 Ω	R_4 Ω	$-V_{BB}$ V	$-V_{BE}$ V	V_i V	V_{BB} V	$-V_i$ V
10	3	1,5	3	3,3	50	220	3,0	1,5	15	12,0	15

$-I_{BM}$ is the reverse current that can flow during switching off. The indicated $-I_{BM}$ is determined and limited by the applied cut-off voltage and series resistance.

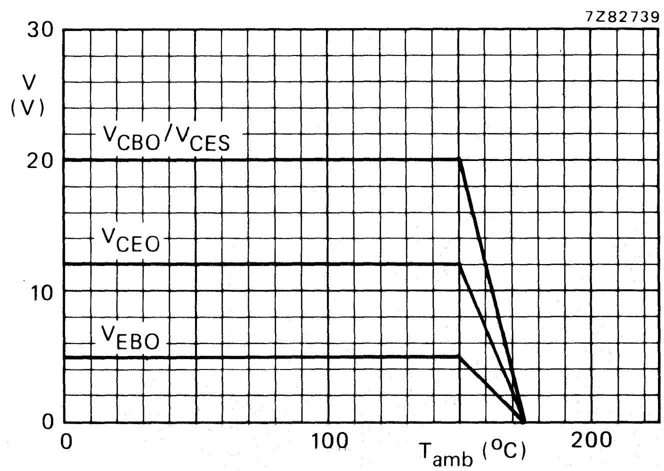


Fig. 4 Voltage derating curves.

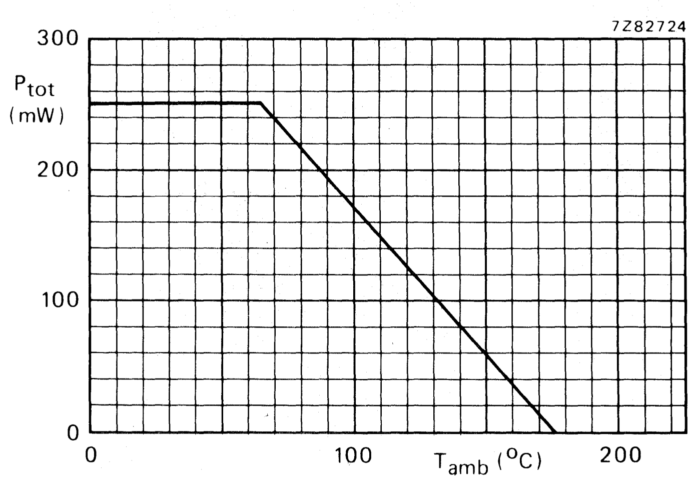


Fig. 5 Power derating curve.

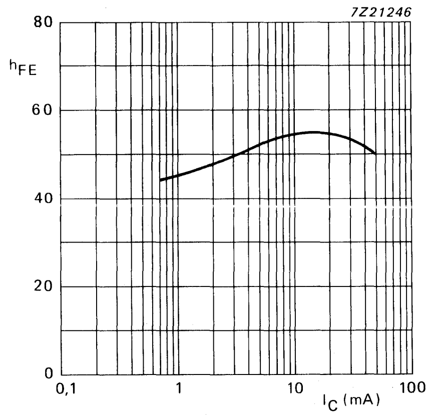


Fig. 6. V_{CE} = 1 V; T_j = 25 °C; typical values.

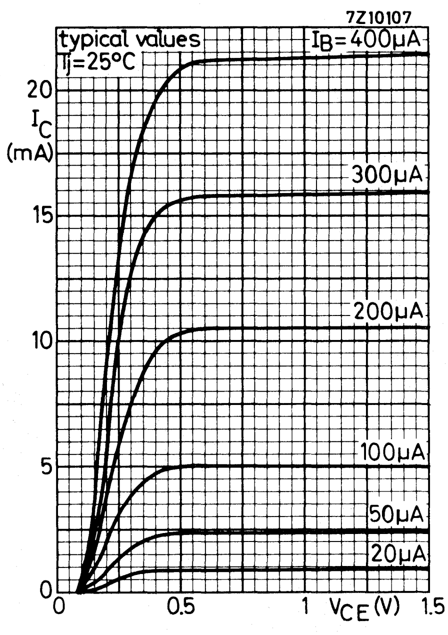


Fig. 7.

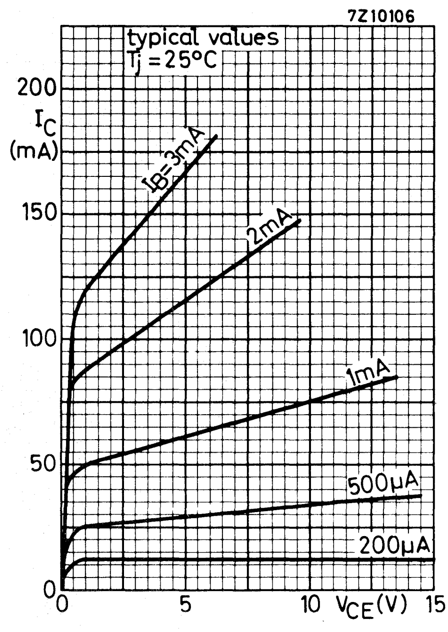


Fig. 8.

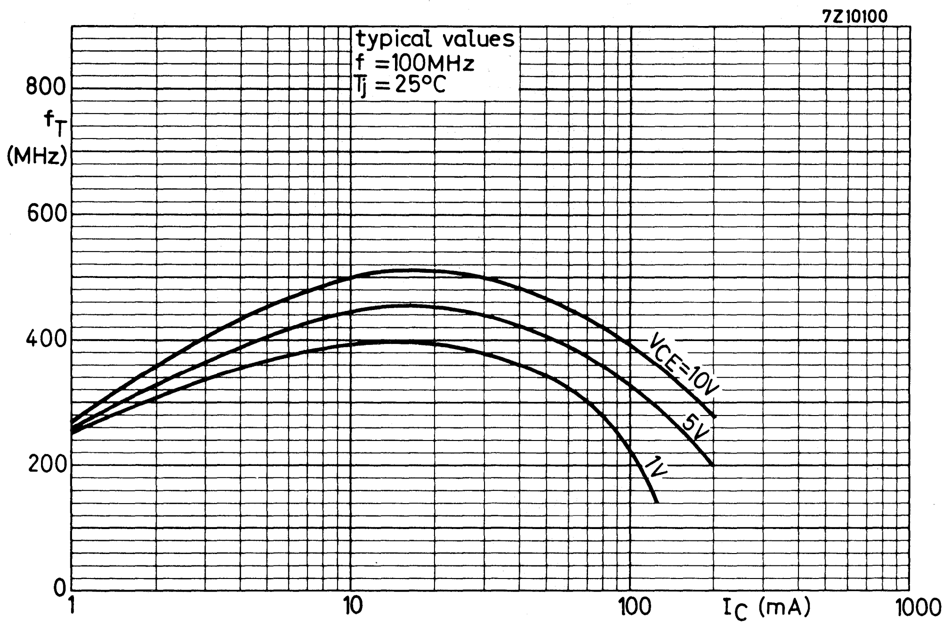

7Z10100
typical values
f = 100MHz
Tj = 25°C
800
fT
(MHz)
600
400
200
0
1
10
100
IC (mA)
1000
VCE=10V
5V
1V

Fig. 9.

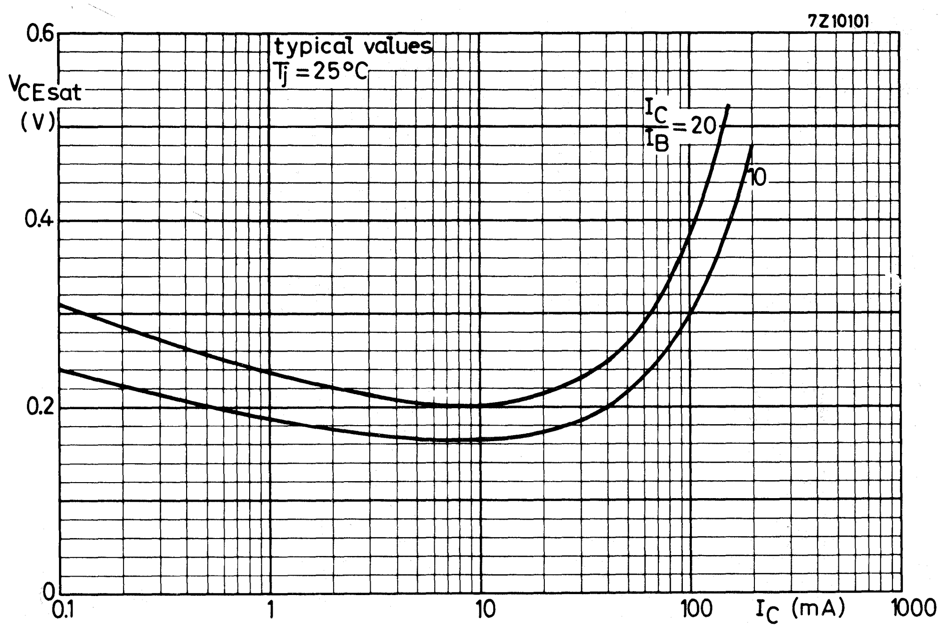

7Z10101
typical values
Tj = 25°C
0.6
VCEsat
(V)
0.4
0.2
0
0.1
1
10
100
IC (mA)
1000
IC/IB = 20
10

Fig. 10.

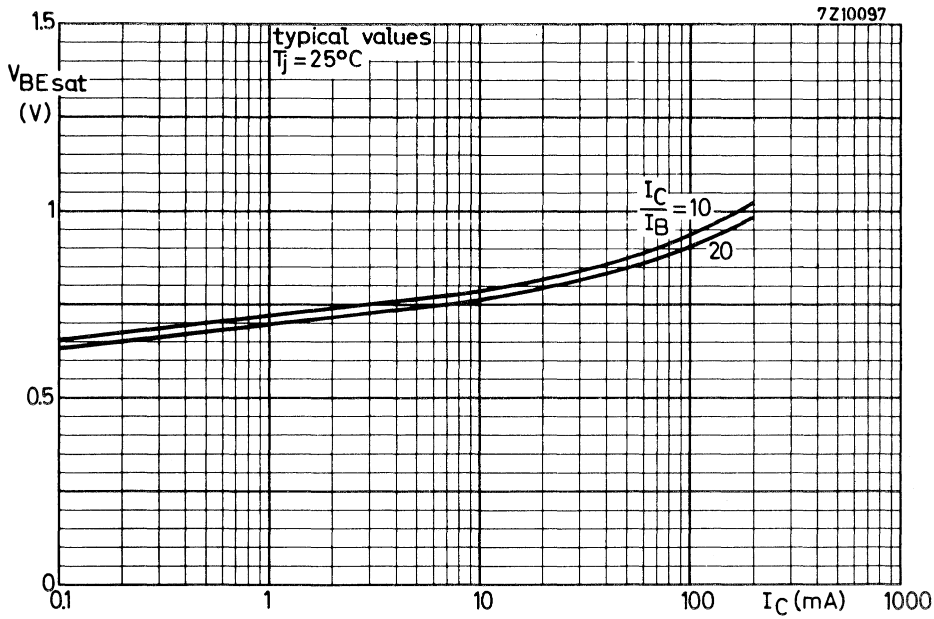


Fig. 11.

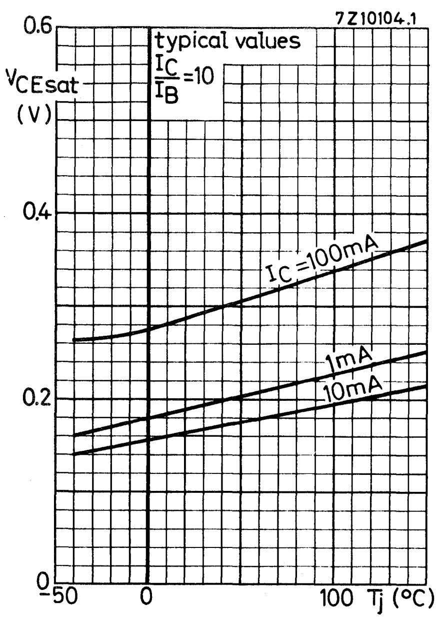


Fig. 12.

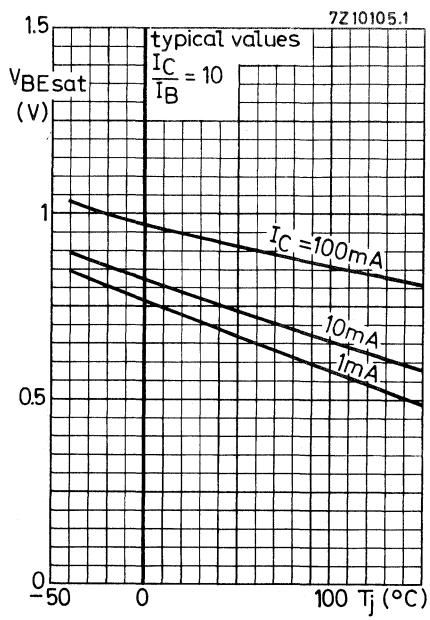


Fig. 13.

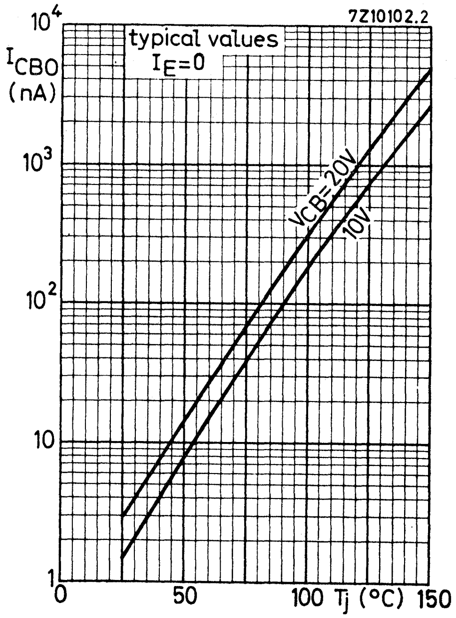

7Z10102.2
typical values
$I_E = 0$
I_{CBO} (nA)
10^4
10^3
10^2
10
1
$V_{CB} = 20V$
10V
0
50
100
T_j (°C)
150

Fig. 14.

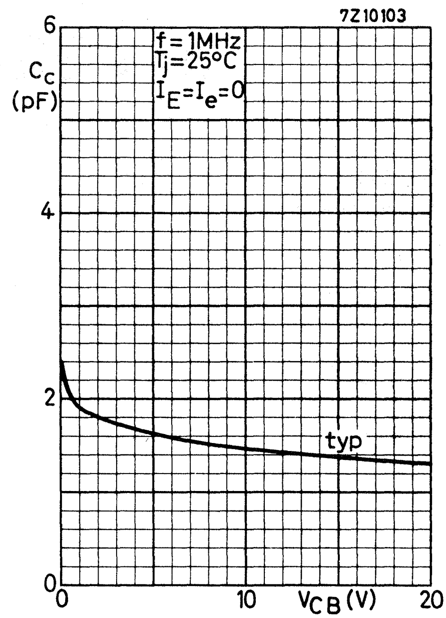

7Z10103
f = 1MHz
$T_j = 25°C$
$I_E = I_e = 0$
C_c (pF)
6
4
2
0
typ
0
10
V_{CB} (V)
20

Fig. 15.

CONTROLLED AVALANCHE RECTIFIER DIODES

Rectifier diodes in hermetically sealed leadless SMID* envelopes and intended for general purpose rectifier applications.

The device is capable of absorbing reverse transient energy.

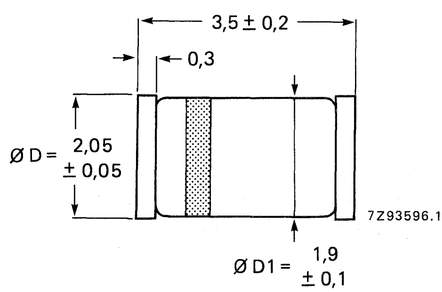
QUICK REFERENCE DATA

			BYD17D	G	J	K	M	
Crest working voltage	V_{RWM}	max.	200	400	600	800	1000	V
Reverse avalanche breakdown voltage	$V_{(BR)R}$	>	225	450	650	900	1100	V
		<	1600	1600	1600	1600	1600	V
Average forward current	$I_{F(AV)}$	max.			1,5			A
Non-repetitive peak forward current	I_{FSM}	max.			20			A
Non-repetitive peak reverse power dissipation	P_{RSM}	max.			0,4			kW
Junction temperature	T_j	max.			175			°C

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-87.



* Surface-mounted implosion diode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BYD17D	G	J	K	M	
Crest working reverse voltage	V_{RWM}	max.	200	400	600	800	1000	V
Continuous reverse voltage	V_R	max.	200	400	600	800	1000	V

Average forward current (averaged over any 20 ms period)				
T_{tp} = 105 °C; lead length 10 mm	$I_{F(AV)}$	max.	1,5	A
T_{amb} = 65 °C; p.c. board mounting	$I_{F(AV)}$	max.	0,6	A
Repetitive peak forward current T_{tp} = 55 °C; f = 50 Hz; a = 3; (inclusive derating for $T_{j\,max}$ at V_{RRM} = 1000 V)	I_{FRM}	max.	5,5	A
Non-repetitive peak forward current t = 10 ms, half-sine wave; T_j = $T_{j\,max}$ prior to surge; $V_R = V_{RWMmax}$	I_{FSM}	max.	20	A
Non-repetitive peak reverse power dissipation; t = 20 μs (half-sine wave); T_j = $T_{j\,max}$ prior to surge	P_{RSM}	max.	0,4	kW
Non-repetitive peak reverse avalanche energy; I_R = 0,34 A; T_j = $T_{j\,max}$ prior to surge; with inductive load switched off	E_{RSM}	max.	7	mJ
Storage temperature	T_{stg}		−65 to + 175	°C
Junction temperature	T_j	max.	175	°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point at a lead length of 10 mm	$R_{th\,j\text{-}tp}$	=	30	K/W
2. Thermal resistance from junction to ambient; device mounted on an 1,5 mm thick epoxy-glass printed circuit board; Cu-thickness ≥ 40 μm (see Fig. 2)	$R_{th\,j\text{-}a}$	=	150	K/W

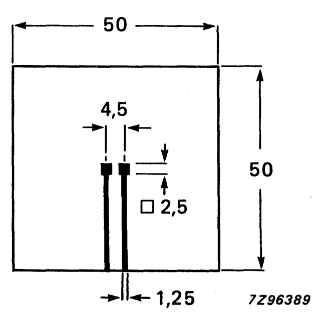


Fig. 2 Mounted on a printed-circuit board.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BYD17D	G	J	K	M	
Forward voltage*								
I_F = 1 A; $T_j = T_{j\,max}$	V_F	<	0,93	0,93	0,93	0,93	0,93	V
I_F = 1 A	V_F	<	1,05	1,05	1,05	1,05	1,05	V
Reverse avalanche breakdown voltage		>	225	450	650	900	1100	V
I_R = 0,1 mA	$V_{(BR)R}$	<	1600	1600	1600	1600	1600	V
Reverse current								
$V_R = V_{RWMmax}$	I_R	<			1			μA
$V_R = V_{RWMmax}$; T_j = 165 °C	I_R	<			100			μA
Diode capacitance								
V_R = 0; f = 1 MHz	C_d	typ.			21			pF

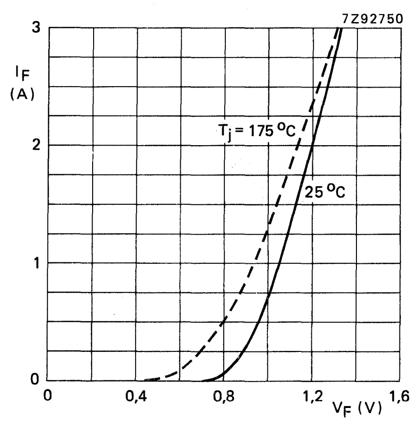


Fig. 3 Maximum forward voltage.

* Measured under pulse conditions to avoid excessive dissipation.

AVALANCHE FAST SOFT-RECOVERY RECTIFIER DIODES

Rectifier diodes in hermetically sealed leadless SMID* envelopes. They are intended for television and industrial applications, such as switched-mode power supplies, scan rectifiers in TV receivers and also for use in inverter and converter applications. The devices feature non-snap-off (soft-recovery) switching characteristics and are capable of absorbing reverse transient energy (e.g. during flashover in a picture tube).

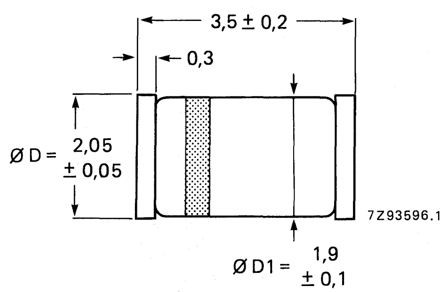
QUICK REFERENCE DATA

			BYD37D	G	J	K	M	
Repetitive peak reverse voltage	V_{RRM}	max.	200	400	600	800	1000	V
Continuous reverse voltage	V_R	max.	200	400	600	600	1000	V
Average forward current	$I_{F(AV)}$	max.		1,5		1,5		A
Non-repetitive peak forward current	I_{FSM}	max.		20		20		A
Non-repetitive peak reverse energy	E_{RSM}	max.		10		7		mJ
Reverse recovery time	t_{rr}	<		250		300		ns

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-87.



* Surface mounted implosion diode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			BYD37D	G	J	K	M	
Repetitive peak reverse voltage	V_{RRM}	max.	200	400	600	800	1000	V
Continuous reverse voltage	V_R	max.	200	400	600	800	1000	V
Average forward current (averaged over any 20 ms period)								
T_{tp} = 105 °C	$I_{F(AV)}$	max.		1,5		1,5		A
T_{amb} = 65 °C; p.c. board mounting	$I_{F(AV)}$	max.		0,6		0,6		A
Repetitive peak forward current	I_{FRM}	max.		12		12		A
Non-repetitive peak forward current t = 10 ms, half-sine wave; T_j = $T_{j\ max}$ prior to surge; $V_R = V_{RRMmax}$	I_{FSM}	max.		20		20		A
Non-repetitive peak reverse avalanche energy; I_R = 400 mA; $T_j = T_{j\ max}$, prior to surge; with inductive load switched off	E_{RSM}	max.		10		7		mJ
Storage temperature	T_{stg}				−65 to +175			°C
Junction temperature	T_j	max.			175			°C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point	$R_{th\ j\text{-}tp}$	=	30	K/W
2. Thermal resistance from junction to ambient; device mounted on a 1,5 mm thick epoxy-glass printed circuit board; Cu-thickness ≥ 40 μm (see Fig. 2)	$R_{th\ j\text{-}a}$	=	150	K/W

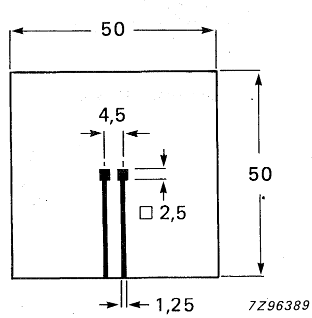


Fig. 2 Mounted on a printed-circuit board.

DEVELOPMENT DATA

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			BYD37D	G	J	K	M	
Forward voltage*								
I_F = 1 A; $T_j = T_{j\,max}$	V_F	<	1,1	1,1	1,1	1,1	1,1	V
I_F = 1 A	V_F	<	1,3	1,3	1,3	1,3	1,3	V
Reverse avalanche breakdown voltage								
I_R = 0,1 mA	$V_{(BR)R}$	>	300	500	700	900	1100	V
Reverse current								
$V_R = V_{RRMmax}$	I_R	<		1		1		μA
$V_R = V_{RRMmax}$; T_j = 165 °C	I_R	<		100		100		μA
Reverse recovery when switched from I_F = 1 A to $V_R \geqslant$ 30 V with $-dI_F/dt$ = 20 A/μs								
recovery charge	Q_s	<		250		400		nC
recovery time	t_{rr}	<		250		300		ns
Maximum slope of reverse recovery current when switched from I_F = 1 A to $V_R \geqslant$ 30 V with $-dI_F/dt$ = 1 A/μs	$\lvert dI_R/dt \rvert$	<		6		5		A/μs

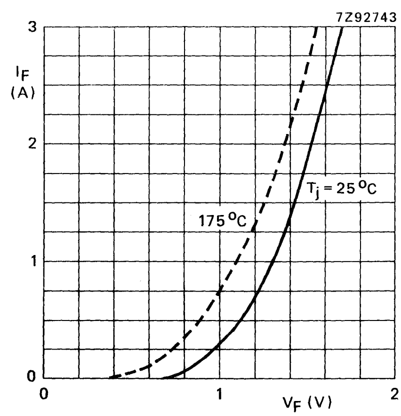


Fig. 3 Maximum forward voltage.

* Measured under pulse conditions to avoid excessive dissipation.

VOLTAGE REGULATOR DIODES

Diodes in hermetically sealed leadless SMID* envelopes.
They are intended for use as voltage regulator in medium power regulator circuits.

The series consists of BZD27-C3V9 to BZD27-C270; diodes in the voltage range 300 V to 510 V are available on request.

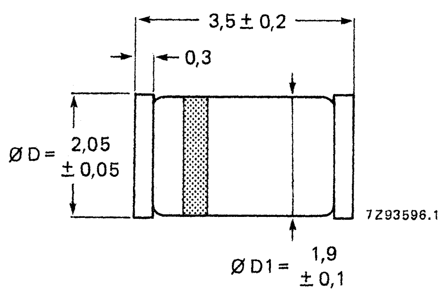
QUICK REFERENCE DATA

Working voltage range	V_Z	nom.	3,9 to 270	V
Working voltage tolerance (E24 range)			± 5	%
Total power dissipation	P_{tot}	max.	2,3	W
Non-repetitive peak reverse power dissipation $T_j = 25\ ^oC$; $t_p = 100\ \mu s$	P_{ZSM}	max.	300	W

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-87.



* Surface mounted implosion diode.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Total power dissipation			
T_{tp} = 105 °C	P_{tot}	max.	2,3 W
T_{amb} = 55 °C; p.c. board mounting	P_{tot}	max.	0,8 W
Non-repetitive peak reverse power dissipation			
t_p = 100 μs square pulse; T_j = 25 °C (prior to surge)	P_{ZSM}	max.	300 W
Storage temperature	T_{stg}		−65 to +175 °C
Junction temperature	T_j	max.	175 °C

THERMAL RESISTANCE

Influence of mounting method

1. Thermal resistance from junction to tie-point	$R_{th\ j\text{-}tp}$	=	30 K/W
2. Thermal resistance from junction to ambient when mounted on a 1,5 mm thick epoxy-glass printed-circuit board; Cu-thickness ⩾ 40 μm (see Fig. 2)	$R_{th\ j\text{-}a}$	=	150 K/W

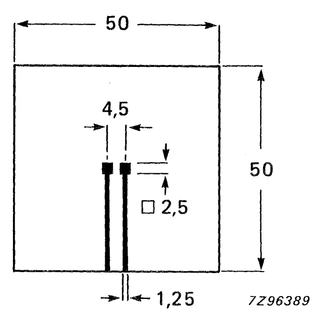


Fig. 2 Mounted on a printed-circuit board.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltage			
I_F = 0,2 A	V_F	<	1,2 V

DEVELOPMENT DATA

CHARACTERISTICS (continued)

BZD27-XXXX	working voltage V_Z V			differential resistance r_{diff} Ω		temperature coefficient S_Z %/K		test current I_Z mA	reverse current I_R µA at	reverse voltage V_R V
	min.	typ.	max.	typ.	max.	min.	max.		max.	
C3V9	3,7	3,9	4,1	4	8	−0,14	−0,04	100	–	–
C4V3	4,0	4,3	4,6	4	7	−0,12	−0,02	100	–	–
C4V7	4,4	4,7	5,0	3	7	−0,10	0	100	–	–
C5V1	4,8	5,1	5,4	3	6	−0,08	0,02	100	100	2
C5V6	5,2	5,6	6,0	2	4	−0,04	0,04	100	50	2
C6V2	5,8	6,2	6,6	2	3	−0,01	0,06	100	20	2
C6V8	6,4	6,8	7,2	1	3	0	0,07	100	200	3
C7V5	7,0	7,5	7,9	1	2	0	0,07	100	50	3
C8V2	7,7	8,2	8,7	1	2	0,03	0,08	100	10	3
C9V1	8,5	9,1	9,6	2	4	0,03	0,08	50	5	5
C10	9,4	10,0	10,6	2	4	0,05	0,09	50	7	7,5
C11	10,4	11,0	11,6	4	7	0,05	0,10	50	3	8,2
C12	11,4	12,0	12,7	4	7	0,05	0,10	50	2	9,1
C13	12,4	13,0	14,1	5	10	0,05	0,10	50	2	10
C15	13,8	15,0	15,6	5	10	0,05	0,10	50	1	11
C16	15,3	16,0	17,1	6	15	0,06	0,11	25	1	12
C18	16,8	18,0	19,1	6	15	0,06	0,11	25	1	13
C20	18,8	20,0	21,2	6	15	0,06	0,11	25	1	15
C22	20,8	22,0	23,3	6	15	0,06	0,11	25	1	16
C24	22,8	24,0	25,6	7	15	0,06	0,11	25	1	18
C27	25,1	27,0	28,9	7	15	0,06	0,11	25	1	20
C30	28	30	32	8	15	0,06	0,11	25	1	22
C33	31	33	35	8	15	0,06	0,11	25	1	24
C36	34	36	38	21	40	0,06	0,11	10	1	27
C39	37	39	41	21	40	0,06	0,11	10	1	30
C43	40	43	46	24	45	0,07	0,12	10	1	33
C47	44	47	50	24	45	0,07	0,12	10	1	36
C51	48	51	54	25	60	0,07	0,12	10	1	39
C56	52	56	60	25	60	0,07	0,12	10	1	43
C62	58	62	66	25	80	0,08	0,13	10	1	47
C68	64	68	72	25	80	0,08	0,13	10	1	51
C75	70	75	79	30	100	0,08	0,13	10	1	56
C82	77	82	87	30	100	0,08	0,13	10	1	62
C91	85	91	96	60	200	0,09	0,13	5	1	68
C100	94	100	106	60	200	0,09	0,13	5	1	75
C110	104	110	116	80	250	0,09	0,13	5	1	82
C120	114	120	127	80	250	0,09	0,13	5	1	91
C130	124	130	141	110	300	0,09	0,13	5	1	100
C150	138	150	156	130	300	0,09	0,13	5	1	110
C160	153	160	171	150	350	0,09	0,13	5	1	120
C180	168	180	191	180	400	0,09	0,13	5	1	130
C200	188	200	212	200	500	0,09	0,13	5	1	150
C220	208	220	233	350	750	0,09	0,13	2	1	160
C240	228	240	256	400	850	0,09	0,13	2	1	180
C270	251	270	289	450	1000	0,09	0,13	2	1	200

Diodes in the voltage range 300 V to 510 V available on request.

SILICON PLANAR VOLTAGE REGULATOR DIODES

Silicon planar voltage regulator diodes, in a SOT-89 plastic envelope, intended for stabilization applications in thick and thin-film circuits.

The series covers the normalized range of nominal working voltages from 2,4 V to 75 V with a tolerance of ± 5% (international standard E24 range).

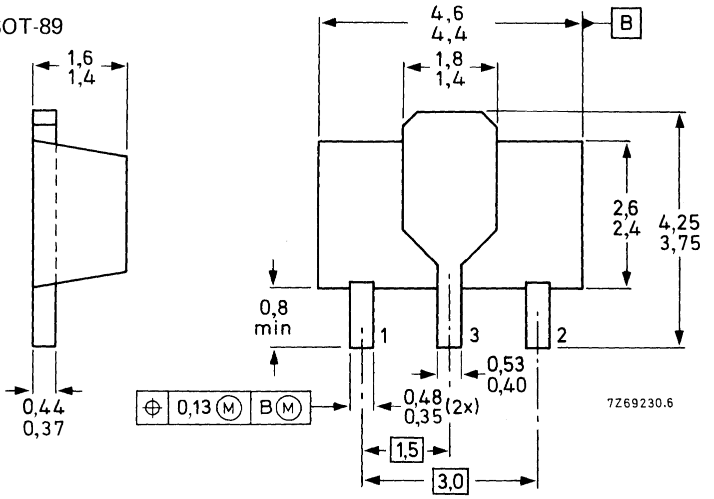
QUICK REFERENCE DATA

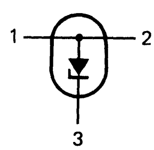
Working voltage range	V_Z	nom.	2,4 to 75	V
Working voltage tolerance (E24 range)			±5	%
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	1	W
Junction temperature	T_j	max.	150	°C

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-89





BOTTOM VIEW

Marking code

BZV49- C2V4 = 2Y4	C5V1 = 5Y1	C12 = 12Y	C33 = 33Y
C2V7 = 2Y7	C5V6 = 5Y6	C13 = 13Y	C36 = 36Y
C3V0 = 3Y0	C6V2 = 6Y2	C15 = 15Y	C39 = 39Y
C3V3 = 3Y3	C6V8 = 6Y8	C16 = 16Y	C43 = 43Y
C3V6 = 3Y6	C7V5 = 7Y5	C18 = 18Y	C47 = 47Y
C3V9 = 3Y9	C8V2 = 8Y2	C20 = 20Y	C51 = 51Y
C4V3 = 4Y3	C9V1 = 9Y1	C22 = 22Y	C56 = 56Y
C4V7 = 4Y7	C10 = 10Y	C24 = 24Y	C62 = 62Y
	C11 = 11Y	C27 = 27Y	C68 = 68Y
		C30 = 30Y	C75 = 75Y

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Repetitive peak forward current	I_{FRM}	max.	250 mA
Average forward current (averaged over any 20 ms period)	$I_{F(AV)}$	max.	250 mA
Working current (d.c.)	I_Z	limited by P_{tot} max	
Total power dissipation * up to T_{amb} = 25 °C	P_{tot}	max.	1 W
Non-repetitive peak reverse power dissipation * T_j = 25 °C; t_p = 100 µs	P_{ZSM}	max.	40 W
Storage temperature	T_{stg}		−65 to +150 °C
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE

From junction to collector tab	$R_{th\ j\text{-}tab}$	=	15 K/W
From junction to ambient in free air *	$R_{th\ j\text{-}a}$	=	125 K/W

CHARACTERISTICS

T_j = 25 °C

Forward voltage I_F = 50 mA		V_F	<	1,0 V
Reverse current BZV49- C2V4	V_R = 1 V	I_R	<	50 µA
C2V7	V_R = 1 V	I_R	<	20 µA
C3V0	V_R = 1 V	I_R	<	10 µA
C3V3	V_R = 1 V	I_R	<	5 µA
C3V6	V_R = 1 V	I_R	<	5 µA
C3V9	V_R = 1 V	I_R	<	3 µA
C4V3	V_R = 1 V	I_R	<	3 µA
C4V7	V_R = 2 V	I_R	<	3 µA
C5V1	V_R = 2 V	I_R	<	2 µA
C5V6	V_R = 2 V	I_R	<	1 µA
C6V2	V_R = 4 V	I_R	<	3 µA
C6V8	V_R = 4 V	I_R	<	2 µA
C7V5	V_R = 5 V	I_R	<	1 µA
C8V2	V_R = 5 V	I_R	<	700 nA
C9V1	V_R = 6 V	I_R	<	500 nA
C10	V_R = 7 V	I_R	<	200 nA
C11 to C13	V_R = 8 V	I_R	<	100 nA
C15 to C75	V_R = 0,7 V_{Znom}	I_R	<	50 nA

* Device mounted on a ceramic substrate: area = 2,5 cm^2; thickness = 0,7 mm.

T_j = 25 °C

E24 logarithmic range (tolerance ± 5%)

BZV49-...	working voltage V_Z (V) at I_{Ztest} = 5 mA		differential resistance r_{diff} (Ω) at I_{Ztest} = 5 mA		temperature coefficient S_Z (mV/K) at I_{Ztest} = 5 mA			diode capacitance C_d(pF); f = 1 MHz V_R = 0	
	min.	max.	typ.	max.	min.	typ.	max.	typ.	max.
C2V4	2,2	2,6	70	100	–3,5	–1,6	0	375	450
C2V7	2,5	2,9	75	100	–3,5	–2,0	0	350	450
C3V0	2,8	3,2	80	95	–3,5	–2,1	0	350	450
C3V3	3,1	3,5	85	95	–3,5	–2,4	0	325	450
C3V6	3,4	3,8	85	90	–3,5	–2,4	0	300	450
C3V9	3,7	4,1	85	90	–3,5	–2,5	0	300	450
C4V3	4,0	4,6	80	90	–3,5	–2,5	0	275	450
C4V7	4,4	5,0	50	80	–3,5	–1,4	0,2	130	180
C5V1	4,8	5,4	40	60	–2,7	–0,8	1,2	110	160
C5V6	5,2	6,0	15	40	–2,0	1,2	2,5	95	140
C6V2	5,8	6,6	6	10	0,4	2,3	3,7	90	130
C6V8	6,4	7,2	6	15	1,2	3,0	4,5	85	110
C7V5	7,0	7,9	6	15	2,5	4,0	5,3	80	100
C8V2	7,7	8,7	6	15	3,2	4,6	6,2	75	95
C9V1	8,5	9,6	6	15	3,8	5,5	7,0	70	90
C10	9,4	10,6	8	20	4,5	6,4	8,0	70	90
C11	10,4	11,6	10	20	5,4	7,4	9,0	65	85
C12	11,4	12,7	10	25	6,0	8,4	10,0	65	85
C13	12,4	14,1	10	30	7,0	9,4	11,0	60	80
C15	13,8	15,6	10	30	9,2	11,4	13,0	55	75
C16	15,3	17,1	10	40	10,4	12,4	14,0	52	75
C18	16,8	19,1	10	45	12,4	14,4	16,0	47	70
C20	18,8	21,2	15	55	14,4	16,4	18,0	36	60
C22	20,8	23,3	20	55	16,4	18,4	20,0	34	60
C24	22,8	25,6	25	70	18,4	20,4	22,0	33	55
	at I_{Ztest} = 2 mA		at I_{Ztest} = 2 mA		at I_{Ztest} = 2 mA				
C27	25,1	28,9	25	80	21,4	23,4	25,3	30	50
C30	28,0	32,0	30	80	24,4	26,6	29,4	27	50
C33	31,0	35,0	35	80	27,4	29,7	33,4	25	45
C36	34,0	38,0	35	90	30,4	33,0	37,4	23	45
C39	37,0	41,0	40	130	33,4	36,4	41,2	21	45
C43	40,0	46,0	45	150	37,6	41,2	46,6	21	40
C47	44,0	50,0	50	170	42,0	46,1	51,8	19	40
C51	48,0	54,0	60	180	46,6	51,0	57,2	19	40
C56	52,0	60,0	70	200	52,2	57,0	63,8	18	40
C62	58,0	66,0	80	215	58,8	64,4	71,6	17	35
C68	64,0	72,0	90	240	65,6	71,7	79,8	17	35
C75	70,0	79,0	95	255	73,4	80,2	88,6	16,5	35

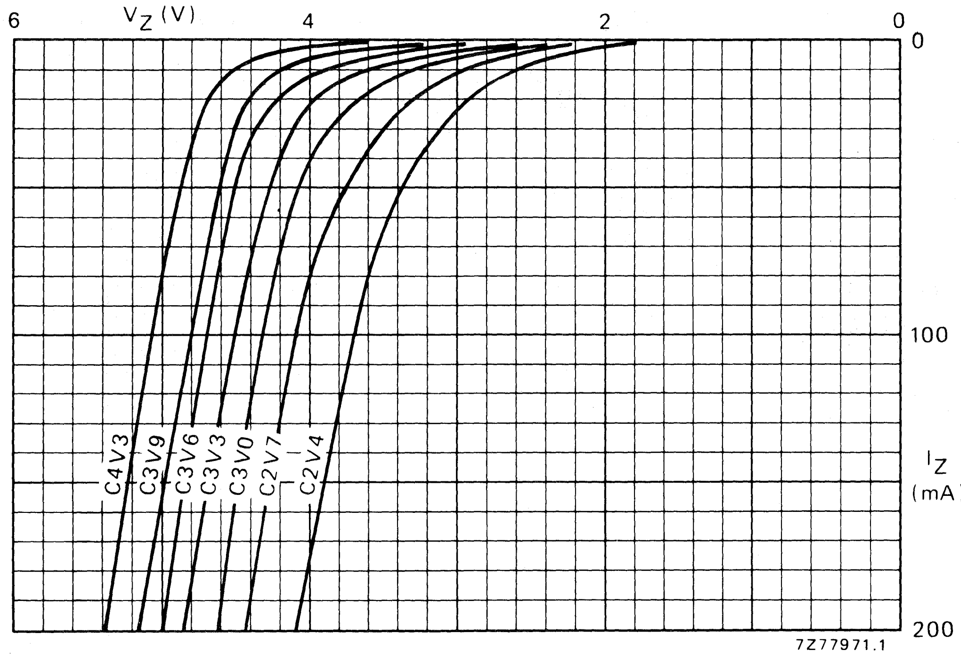


Fig. 2 Dynamic characteristics; typical values; T_j = 25 °C.

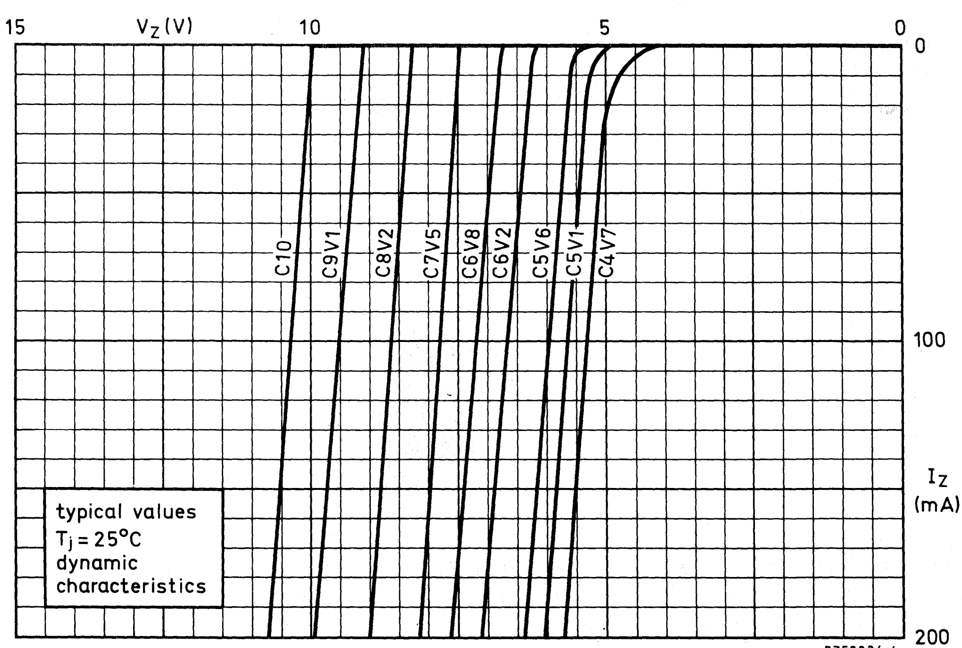


Fig. 3 Dynamic characteristics; typical values at T_j = 25 °C.

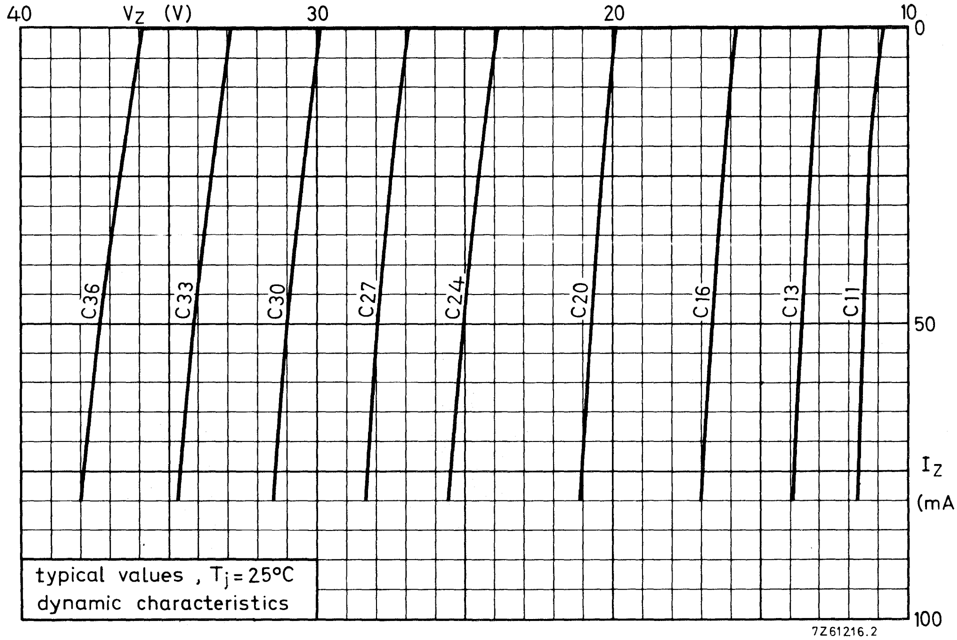


Fig. 4 Dynamic characteristics; typical values; T_j = 25 °C.

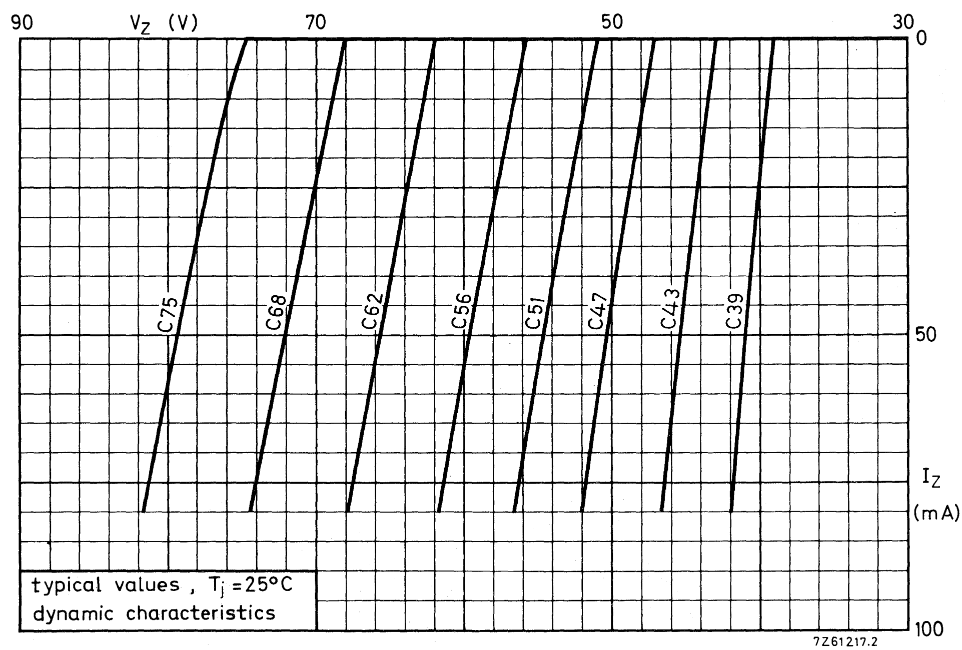


Fig. 5 Dynamic characteristics; typical values at T_j = 25 °C.

Model for calculating the static working voltage ($V_{Z\ stat}$).

This model can be derived from $V_{Z\ stat} = V_{Z\ dyn} + \Delta V_Z$ of which $V_{Z\ dyn}$ is given in the preceding tables and can be derived from the typical dynamic characteristic curves (Figs 2, 3, 4 and 5)
$\Delta V_Z = \Delta T \times S_Z$. For S_Z see tables and graphs S_Z versus T_j.
$\Delta T = P_{tot} \times R_{th\ j\text{-}a} = I_Z \times V_{Z\ dyn} \times R_{th\ j\text{-}a}$.
Following $\Delta V_Z = I_Z \times V_{Z\ dyn} \times R_{th\ j\text{-}a} \times S_Z$ and the model will be:

$$V_{Z\ stat} = V_{Z\ dyn} + I_Z \times V_{Z\ dyn} \times R_{th\ j\text{-}a} \times S_Z$$

Calculating example

BZV49-C24 mounted on a ceramic substrate of 7 x 5 x 0,6 mm; at I_Z = 7 mA.

$$V_{Z\ stat} = 24 + (\frac{7}{1000} \times 24 \times \frac{125}{1000} \times 20{,}3)$$
$$= 24 + 0{,}4 = 24{,}4\ V.$$

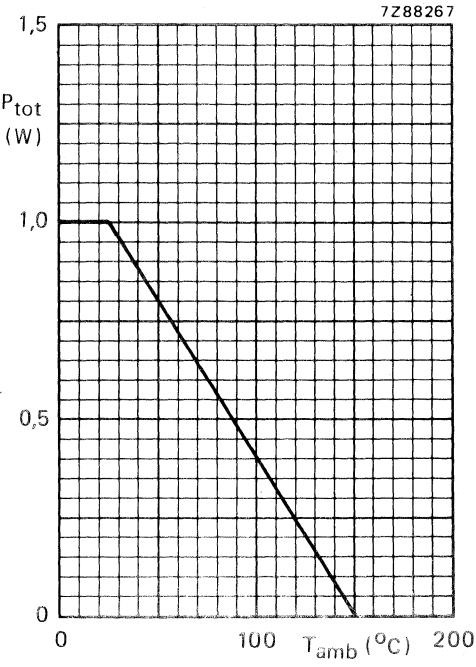


Fig. 6 Power derating curve.

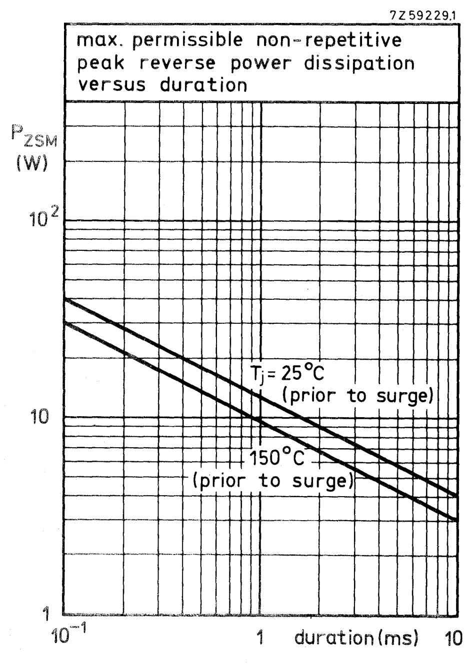


Fig. 7.

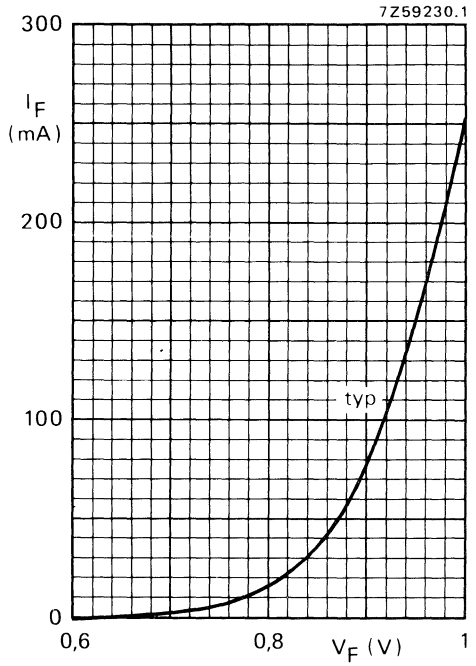


Fig. 8 T_j = 25 °C.

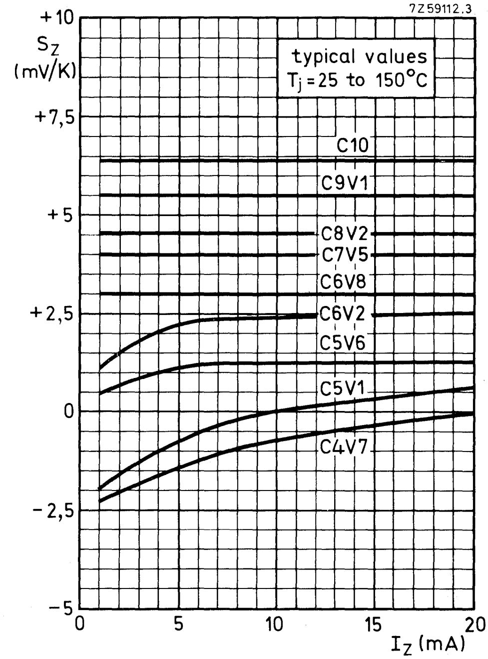


Fig. 9.

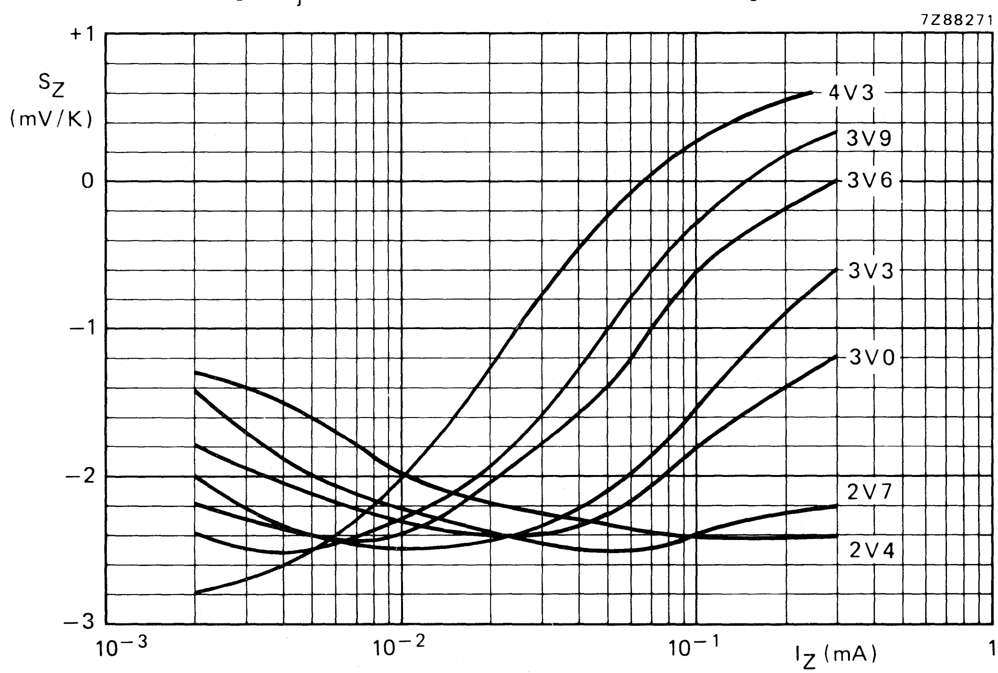


Fig. 10 Typical values temperature coefficient.

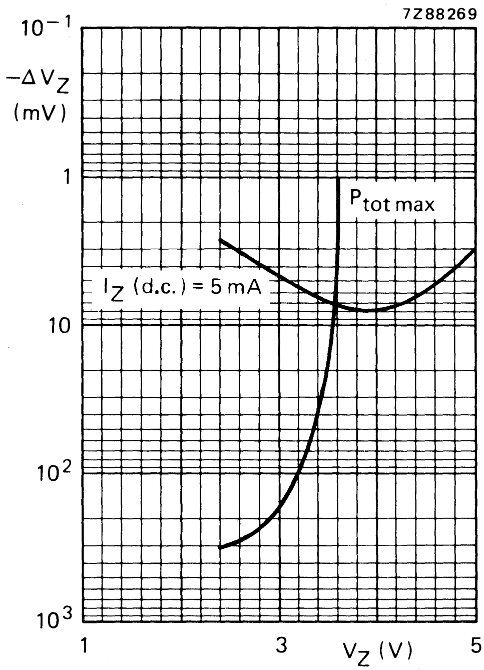


Fig. 11 Typical change of working voltage; T_j = 25 °C.

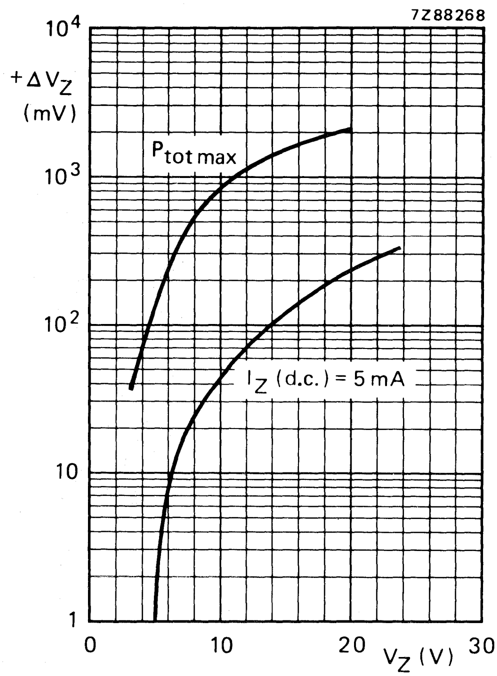


Fig. 12 Typical change of working voltage; T_{amb} = 25 °C.

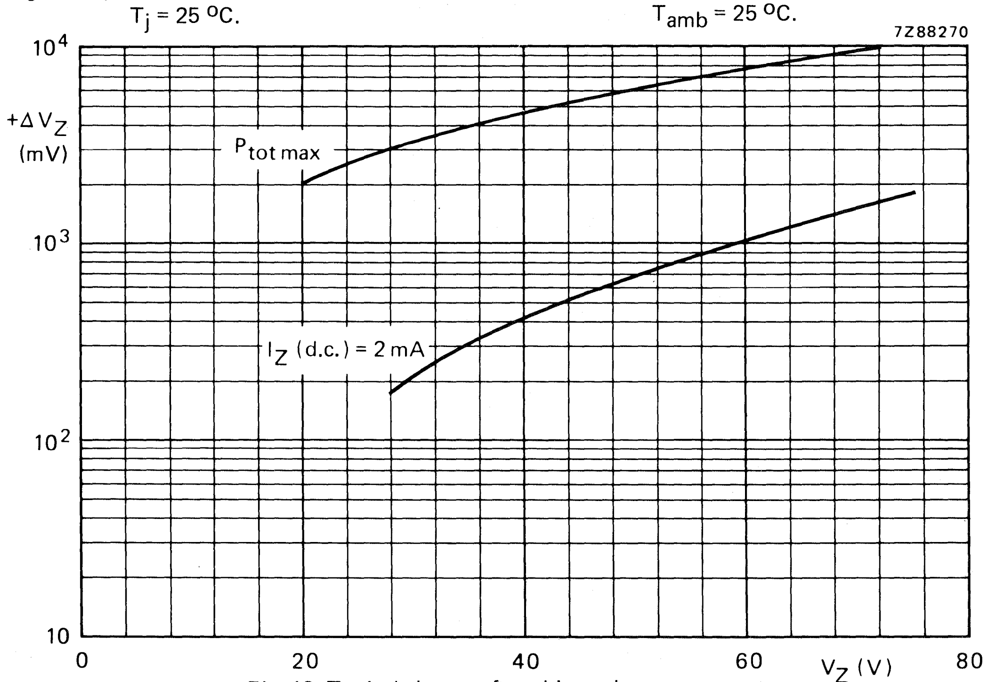


Fig. 13 Typical change of working voltage.

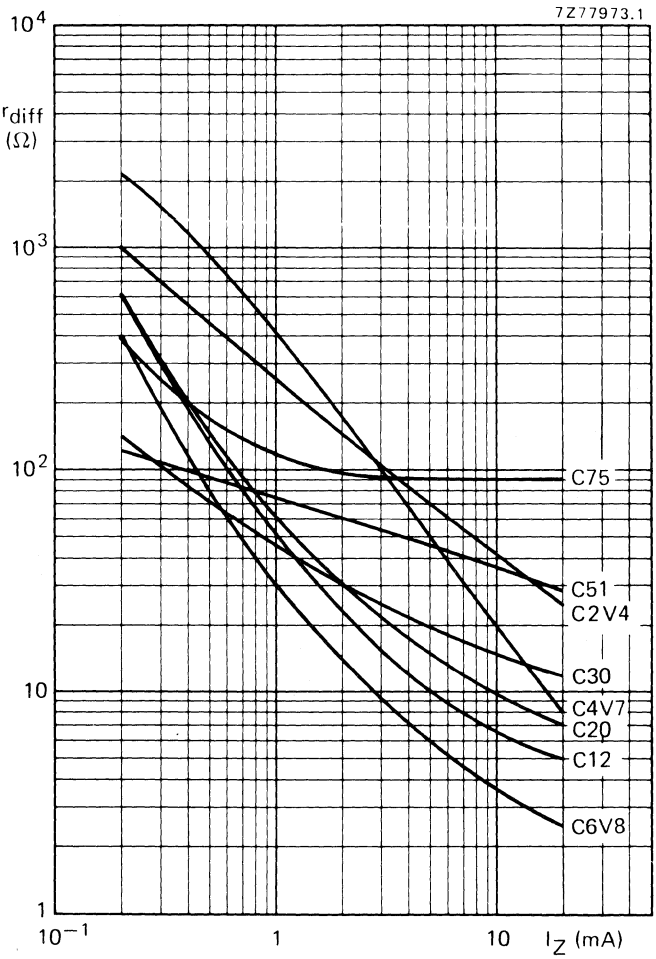


Fig. 14 Typical values; T_j = 25 °C; f = 1 kHz.

VOLTAGE REGULATOR DIODES FOR SURFACE MOUNTING

Silicon planar diodes designed for use as low-voltage stabilizers or voltage references.
They are available in the international standardized E24 (±5%) range. The series consists of 37 types with nominal working voltages ranging from 2,4 V to 75 V.

The SM diode is a leadless diode in an hermetically sealed glass SOD-80 envelope with tinplated metal discs at each end. It is suitable for "automatic placement" and as such it can withstand immersion soldering.

The diodes are delivered in "super 8" tape.

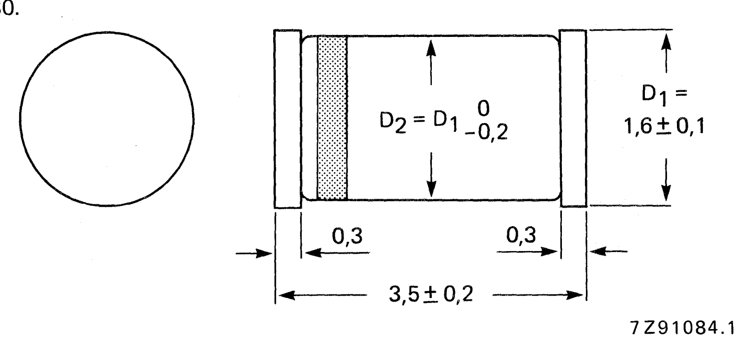
QUICK REFERENCE DATA

Working voltage range	V_Z	nom.	2,4 to 75	V
Total power dissipation up to flange temperature of 50 °C	P_{tot}	max.	500	mW
Non-repetitive peak reverse power dissipation	P_{ZSM}	max.	30	W
Junction temperature	T_j	max.	200	°C
Thermal resistance from junction to tie-point	$R_{th\ j\text{-}tp}$	=	0,30	K/mW

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-80.



The BZV55 cathode is indicated by a yellow band.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134).

Average forward current (averaged over any 20 ms period)	$I_{F(AV)}$	max.	250 mA
Repetitive peak forward current	I_{FRM}	max.	250 mA
Total power dissipation up to T_{flange} = 50 °C	P_{tot}	max.	500 mW
up to T_{amb} = 50 °C and mounted on a ceramic substrate of 10 mm x 10 mm x 0,6 mm	P_{tot}	max.	400 mW
Non-repetitive peak reverse power dissipation t = 100 μs; T_j = 150 °C	P_{ZSM}	max.	30 W
Storage temperature	T_{stg}	−65 to +200 °C	
Junction temperature	T_j	max.	200 °C

THERMAL RESISTANCE

From junction to tie-point (flanges)	$R_{th\ j\text{-}tp}$	=	0,30 K/mW
From junction to ambient when mounted on a ceramic substrate of 10 mm x 10 mm x 0,6 mm	$R_{th\ j\text{-}a}$	=	0,38 K/mW

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltage

I_F = 10 mA		V_F	<	0,9 V

Reverse current

BZV55-.2V4	V_R = 1 V	I_R	<	50 μA
.2V7	V_R = 1 V	I_R	<	20 μA
.3V0	V_R = 1 V	I_R	<	10 μA
.3V3	V_R = 1 V	I_R	<	5 μA
.3V6	V_R = 1 V	I_R	<	5 μA
.3V9	V_R = 1 V	I_R	<	3 μA
.4V3	V_R = 1 V	I_R	<	3 μA
.4V7	V_R = 2 V	I_R	<	3 μA
.5V1	V_R = 2 V	I_R	<	2 μA
.5V6	V_R = 2 V	I_R	<	1 μA
.6V2	V_R = 4 V	I_R	<	3 μA
.6V8	V_R = 4 V	I_R	<	2 μA
.7V5	V_R = 5 V	I_R	<	1 μA
.8V2	V_R = 5 V	I_R	<	700 nA
.9V1	V_R = 6 V	I_R	<	500 nA
.10	V_R = 7 V	I_R	<	200 nA
.11 to .13	V_R = 8 V	I_R	<	100 nA
.15 to .75	V_R = 0,7 V_{Znom}	I_R	<	50 nA

. = C for E24 (± 5%) tolerance

T_j = 25 °C

E24 (± 5%) logarithmic range

BZV55- ...	working voltage V_Z (V) at I_{Ztest} = 5 mA		differential resistance r_{diff} (Ω) at I_{Ztest} = 5 mA		temperature coefficient S_Z (mV/K) at I_{Ztest} = 5 mA			diode capacitance C_d (pF) at f = 1 MHz V_R = 0	
	min.	max.	typ.	max.	min.	typ.	max.	typ.	max.
C2V4	2,2	2,6	70	100	−3,5	−1,6	0	375	450
C2V7	2,5	2,9	75	100	−3,5	−2,0	0	350	450
C3V0	2,8	3,2	80	95	−3,5	−2,1	0	350	450
C3V3	3,1	3,5	85	95	−3,5	−2,4	0	325	450
C3V6	3,4	3,8	85	90	−3,5	−2,4	0	300	450
C3V9	3,7	4,1	85	90	−3,5	−2,5	0	300	450
C4V3	4,0	4,6	80	90	−3,5	−2,5	0	275	450
C4V7	4,4	5,0	50	80	−3,5	−1,4	0,2	125	180
C5V1	4,8	5,4	40	60	−2,7	−0,8	1,2	125	180
C5V6	5,2	6,0	15	40	−2,0	1,2	2,5	125	180
C6V2	5,8	6,6	6	10	0,4	2,3	3,7	90	130
C6V8	6,4	7,2	6	15	1,2	3,0	4,5	85	110
C7V5	7,0	7,9	6	15	2,5	4,0	5,3	80	100
C8V2	7,7	8,7	6	15	3,2	4,6	6,2	75	95
C9V1	8,5	9,6	6	15	3,8	5,5	7,0	70	90
C10	9,4	10,6	8	20	4,5	6,4	8,0	70	90
C11	10,4	11,6	10	20	5,4	7,4	9,0	65	85
C12	11,4	12,7	10	25	6,0	8,4	10,0	65	85
C13	12,4	14,1	10	30	7,0	9,4	11,0	60	80
C15	13,8	15,6	10	30	9,2	11,4	13,0	55	75
C16	15,3	17,1	10	40	10,4	12,4	14,0	52	75
C18	16,8	19,1	10	45	12,4	14,4	16,0	47	70
C20	18,8	21,2	15	55	14,4	16,4	18,0	36	60
C22	20,8	23,3	20	55	16,4	18,4	20,0	34	60
C24	22,8	25,6	25	70	18,4	20,4	22,0	33	55
	at I_{Ztest} = 2 mA		at I_{Ztest} = 2 mA		at I_{Ztest} = 2 mA				
C27	25,1	28,9	25	80	21,4	23,4	25,3	30	50
C30	28,0	32,0	30	80	24,4	26,6	29,4	27	50
C33	31,0	35,0	35	80	27,4	29,7	33,4	25	45
C36	34,0	38,0	35	90	30,4	33,0	37,4	23	45
C39	37,0	41,0	40	130	33,4	36,4	41,2	21	45
C43	40,0	46,0	45	150	37,6	41,2	46,6	21	40
C47	44,0	50,0	50	170	42,0	46,1	51,8	19	40
C51	48,0	54,0	60	180	46,6	51,0	57,2	19	40
C56	52,0	60,0	70	200	52,2	57,0	63,8	18	40
C62	58,0	66,0	80	215	58,8	64,4	71,6	17	35
C68	64,0	72,0	90	240	65,6	71,7	79,8	17	35
C75	70,0	79,0	95	255	73,4	80,2	88,6	16,5	35

T_j = 25 °C
E24 (± 5%) logarithmic range

BZV55- ...	working voltage V_Z (V) at I_Z = 1 mA			differential resistance r_{diff} (Ω) at I_Z = 1 mA		working voltage V_Z (V) at I_Z = 20 mA			differential resistance r_{diff} (Ω) at I_Z = 20 mA	
	min.	nom.	max.	typ.	max.	min.	nom.	max.	typ.	max.
C2V4	1,7	1,9	2,1	275	600	2,6	2,9	3,2	25	50
C2V7	1,9	2,2	2,4	300	600	3,0	3,3	3,6	25	50
C3V0	2,1	2,4	2,7	325	600	3,3	3,6	3,9	25	50
C3V3	2,3	2,6	2,9	350	600	3,6	3,9	4,2	20	40
C3V6	2,7	3,0	3,3	375	600	3,9	4,2	4,5	20	40
C3V9	2,9	3,2	3,5	400	600	4,1	4,4	4,7	15	30
C4V3	3,3	3,6	4,0	410	600	4,4	4,7	5,1	15	30
C4V7	3,7	4,2	4,7	425	500	4,5	5,0	5,4	8	15
C5V1	4,2	4,7	5,3	400	480	5,0	5,4	5,9	6	15
C5V6	4,8	5,4	6,0	80	400	5,2	5,7	6,3	4	10
C6V2	5,6	6,1	6,6	40	150	5,8	6,3	6,8	3	6
C6V8	6,3	6,7	7,2	30	80	6,4	6,9	7,4	2,5	6
C7V5	6,9	7,4	7,9	30	80	7,0	7,6	8,0	2,5	6
C8V2	7,6	8,1	8,7	40	80	7,7	8,3	8,8	3	6
C9V1	8,4	9,0	9,6	40	100	8,5	9,2	9,7	4	8
C10	9,3	9,9	10,6	50	150	9,4	10,1	10,7	4	10
C11	10,2	10,9	11,6	50	150	10,4	11,1	11,8	5	10
C12	11,2	11,9	12,7	50	150	11,4	12,1	12,9	5	10
C13	12,3	12,9	14,0	50	170	12,5	13,1	14,2	5	15
C15	13,7	14,9	15,5	50	200	13,9	15,1	15,7	6	20
C16	15,2	15,9	17,0	50	200	15,4	16,1	17,2	6	20
C18	16,7	17,9	19,0	50	225	16,9	18,1	19,2	6	20
C20	18,7	19,9	21,1	60	225	18,9	20,1	21,4	7	20
C22	20,7	21,9	23,2	60	250	20,9	22,1	23,4	7	25
C24	22,7	23,9	25,5	60	250	22,9	24,1	25,7	7	25
	at I_Z = 0,1 mA			at I_Z = 0,5 mA		at I_Z = 10 mA			at I_Z = 10 mA	
C27	25,0	26,9	28,9	65	300	25,2	27,1	29,3	10	45
C30	27,8	29,9	32,0	70	300	28,1	30,1	32,4	15	50
C33	30,8	32,9	35,0	75	325	31,1	33,1	35,4	20	55
C36	33,8	35,9	38,0	80	350	34,1	36,1	38,4	25	60
C39	36,7	38,9	41,0	80	350	37,1	39,1	41,5	25	70
C43	39,7	42,9	46,0	85	375	40,1	43,1	46,5	25	80
C47	43,7	46,8	50,0	85	375	44,1	47,1	50,5	30	90
C51	47,6	50,8	54,0	90	400	48,1	51,1	54,6	35	100
C56	51,5	55,7	60,0	100	425	52,1	56,1	60,8	45	110
C62	57,4	61,7	66,0	120	450	58,2	62,1	67,0	60	120
C68	63,4	67,7	72,0	150	475	64,2	68,2	73,2	75	130
C75	69,4	74,7	79,0	170	500	70,3	75,3	80,2	90	140

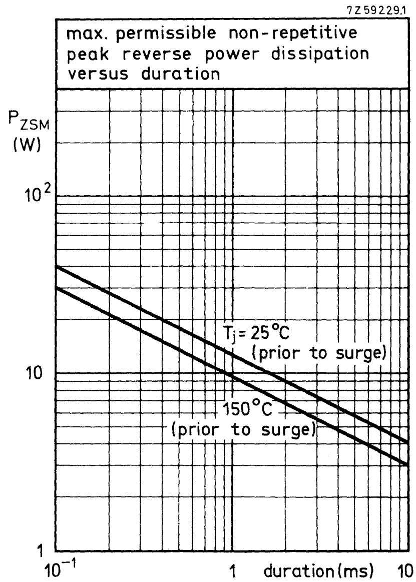


Fig. 2.

DEVELOPMENT DATA

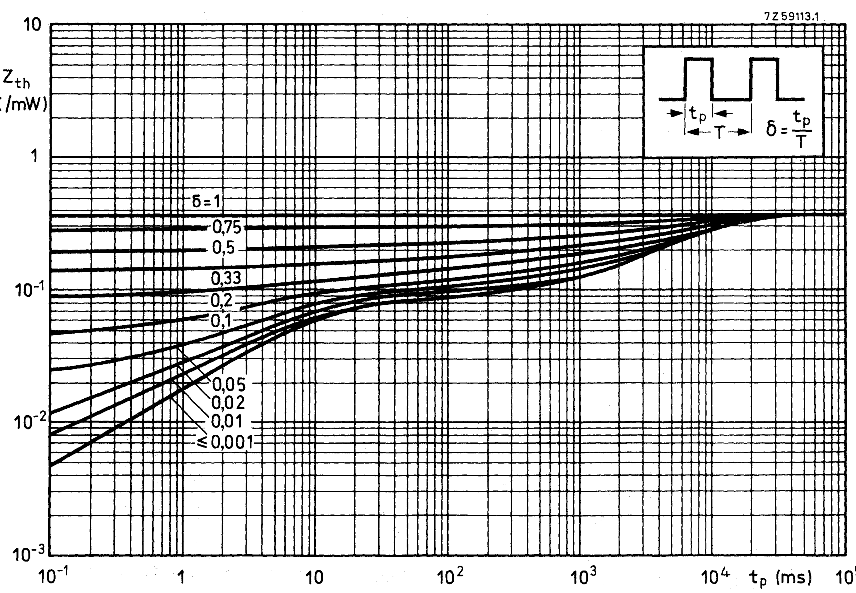


Fig. 3.

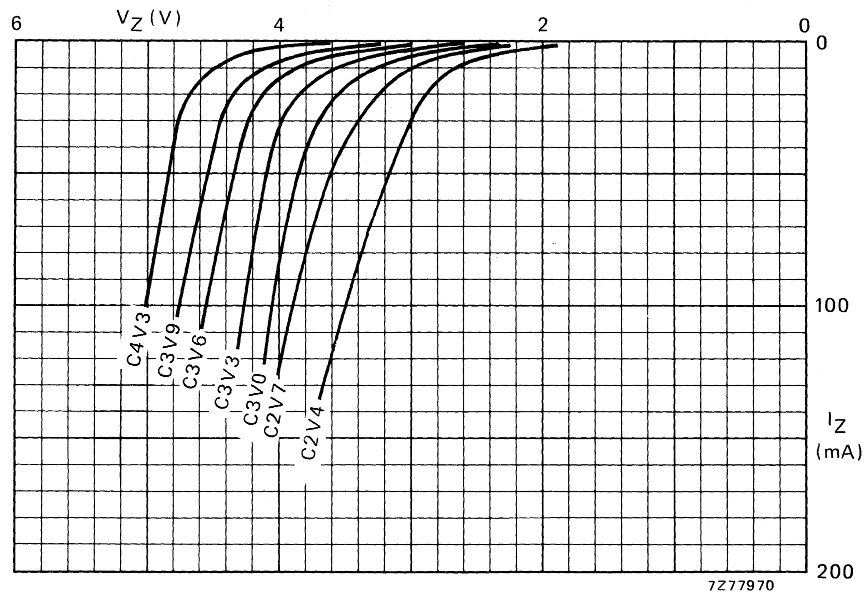


Fig. 4 Static characteristics; typical values; T_{amb} = 25 °C.

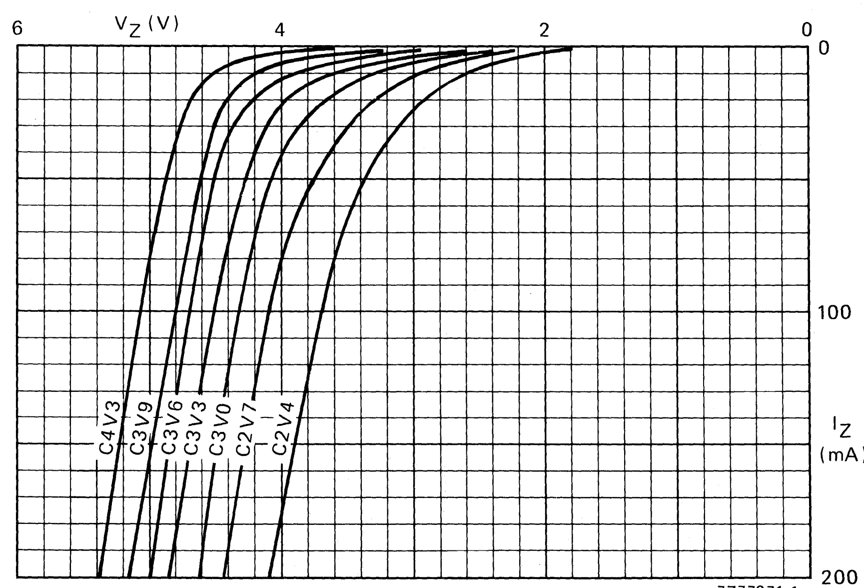


Fig. 5 Dynamic characteristics; typical values; T_j = 25 °C.

DEVELOPMENT DATA

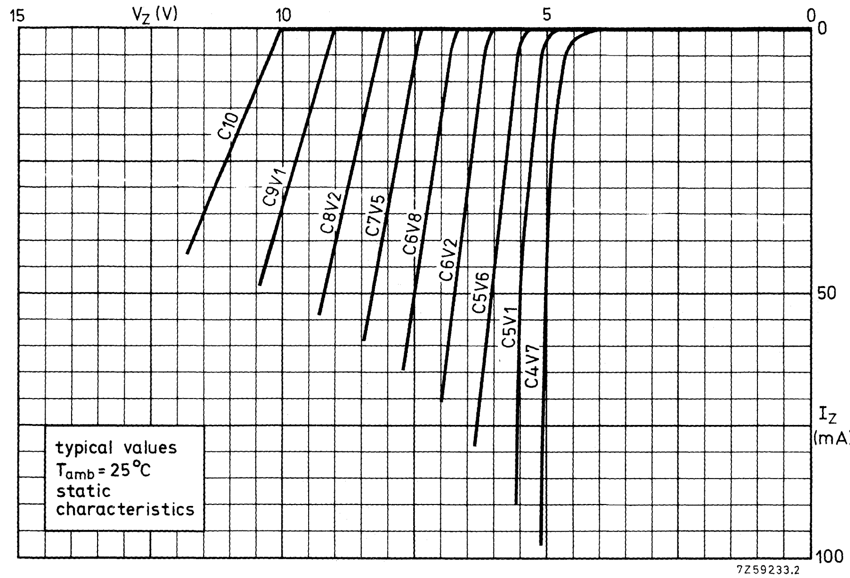


Fig. 6.

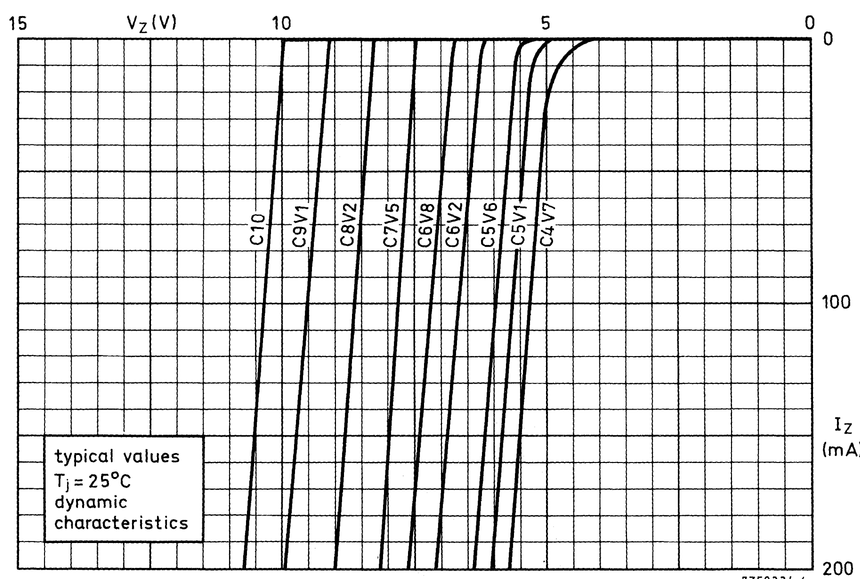
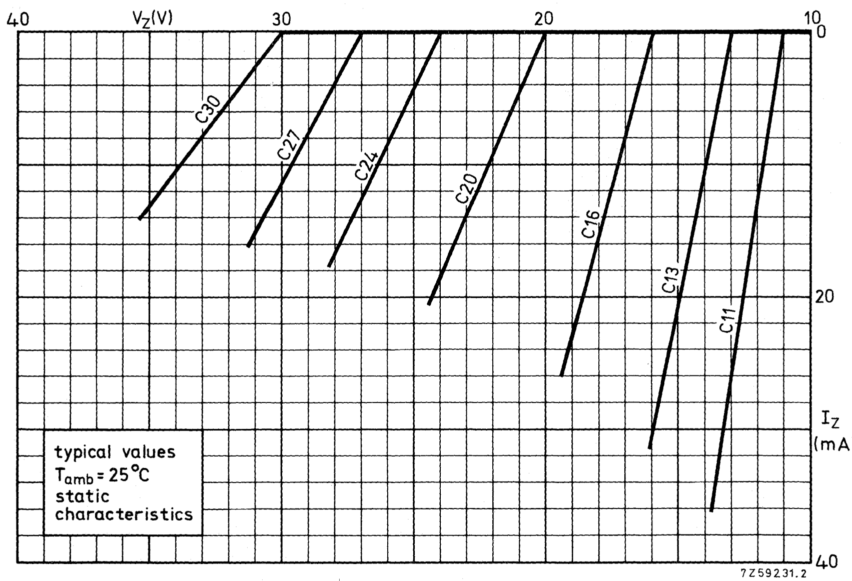
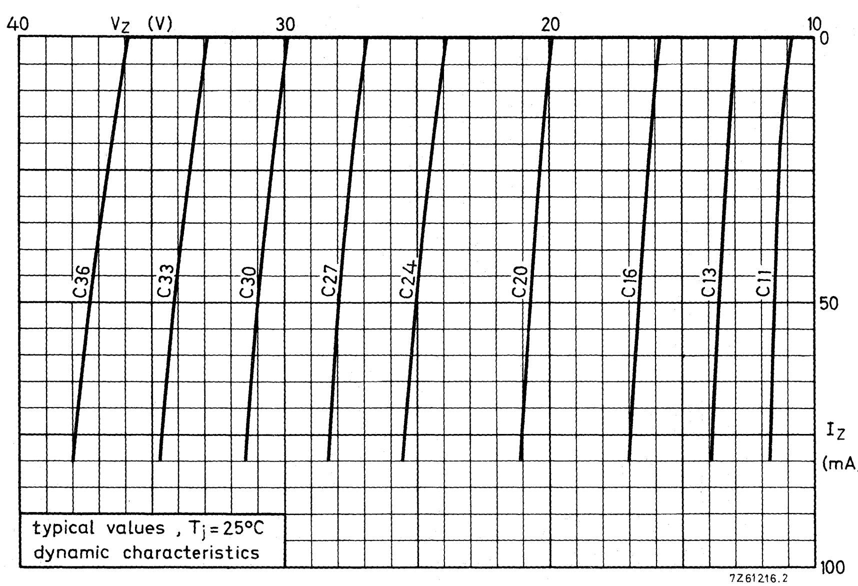


Fig. 7.



40
V_Z(V)
30
20
10
0
C30
C27
C24
C20
C16
C13
C11
20
I_Z
(mA)
40
typical values
$T_{amb} = 25\,^{\circ}C$
static
characteristics
7Z59231.2

Fig. 8.



40
V_Z (V)
30
20
10
0
C36
C33
C30
C27
C24
C20
C16
C13
C11
50
I_Z
(mA)
100
typical values , $T_j = 25\,^{\circ}C$
dynamic characteristics
7Z61216.2

Fig. 9.

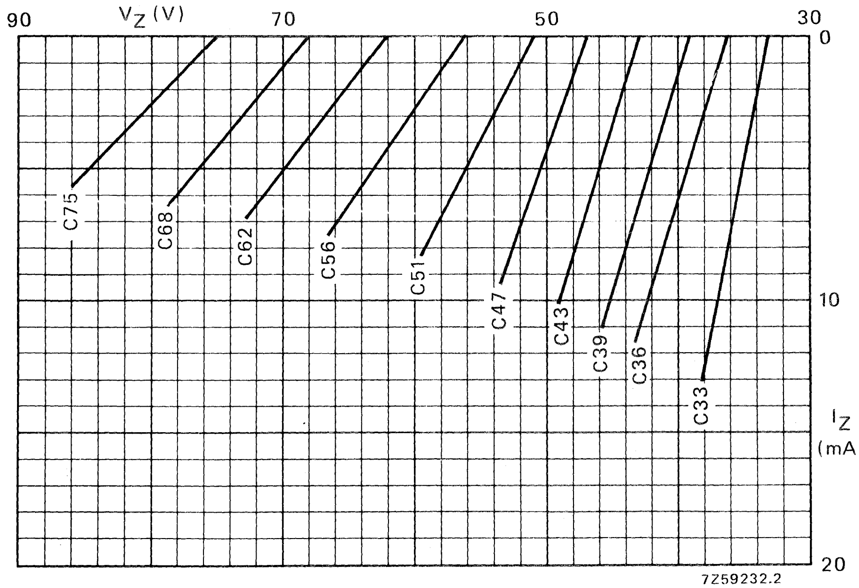


Fig. 10 Static characteristics; typical values; T_{amb} = 25 °C.

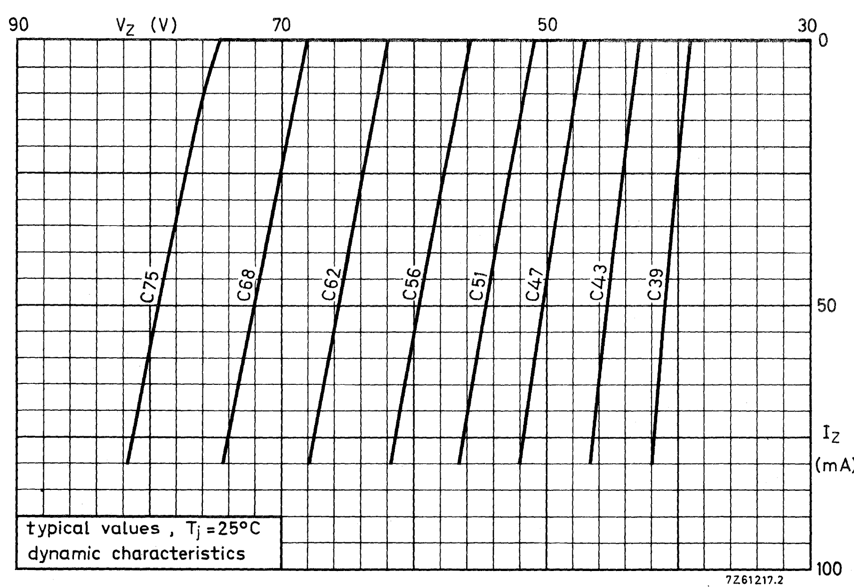


Fig. 11.

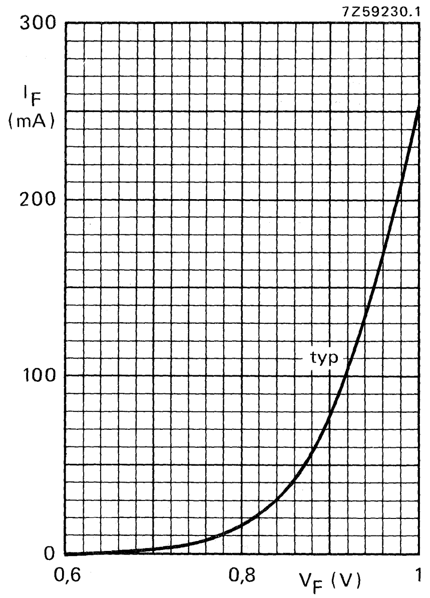


Fig. 12 T_j = 25 °C.

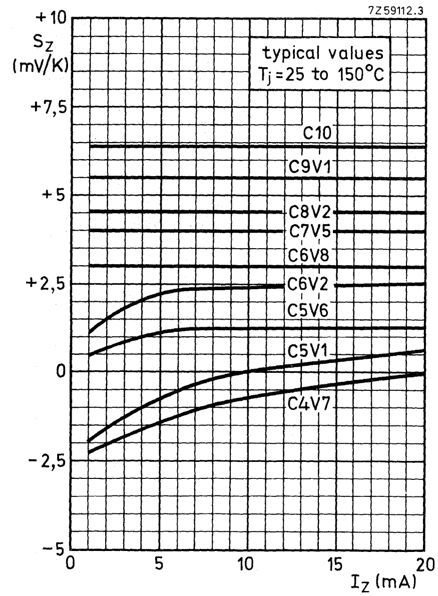


Fig. 13.

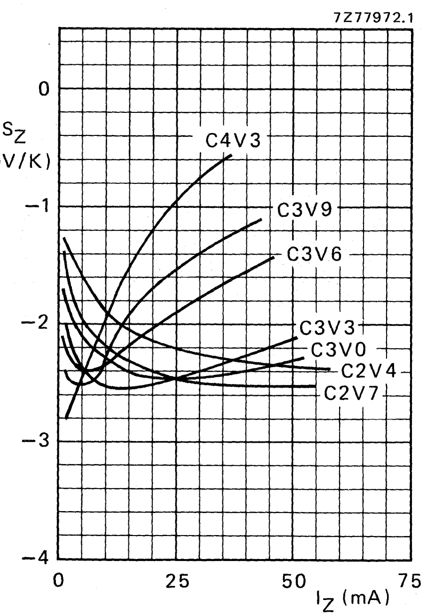


Fig. 14 Typical values; T_j = 25 to 150 °C.

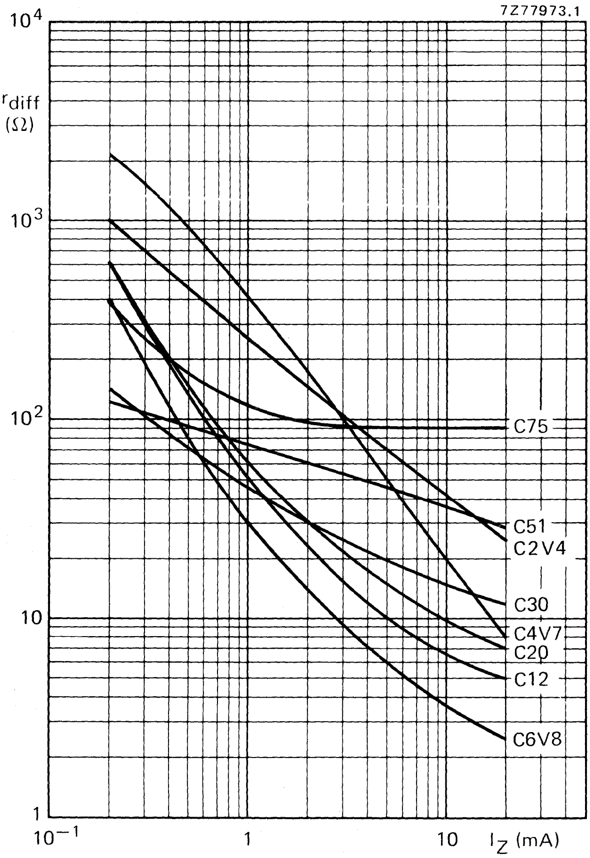


Fig. 15 Typical values; T_j = 25 °C; f = 1 kHz.

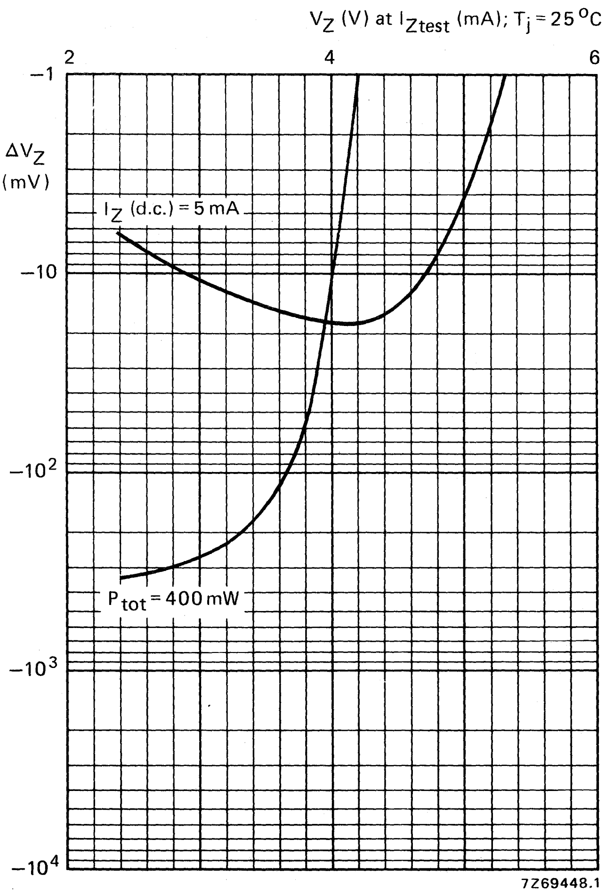


Fig. 16 Typical change of working voltage under operating conditions at T_{amb} = 25 °C.

DEVELOPMENT DATA

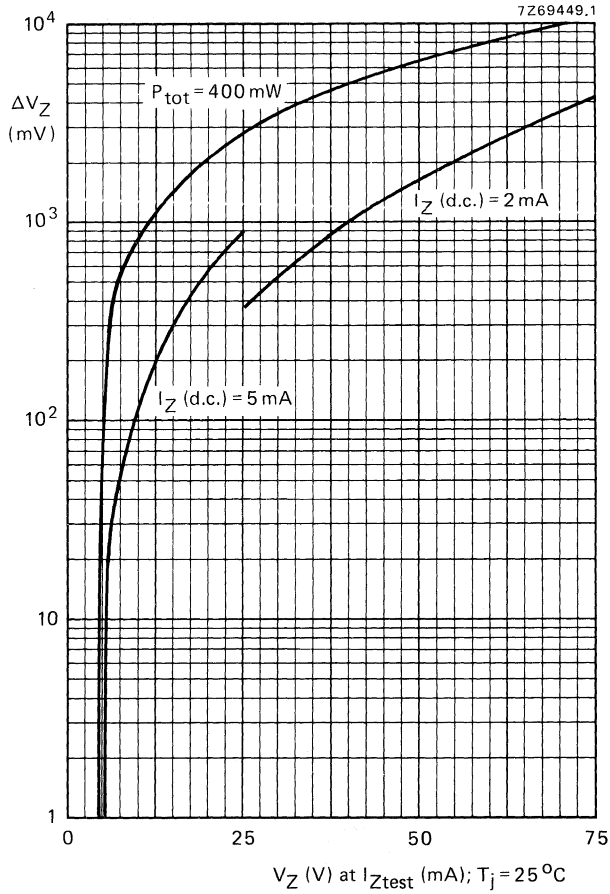


Fig. 17 Typical change of working voltage under operating conditions at $T_{amb} = 25\ ^oC$.

SILICON PLANAR VOLTAGE REGULATOR DIODES

Low power general purpose voltage regulator diodes in a microminiature plastic envelope intended for application in thick and thin-film circuits. The series covers the normalized range of nominal working voltages from 2,4 V to 75 V with a working voltage tolerance of ± 5%.

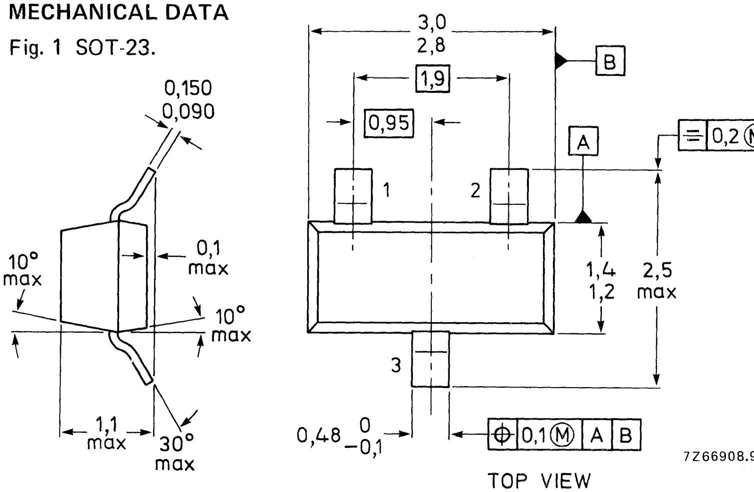
QUICK REFERENCE DATA

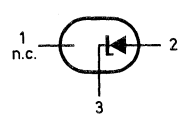
Working voltage range	V_Z	nom.	2,4 to 75	V
Working voltage tolerance			± 5	%
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	350	mW
Junction temperature	T_j	max.	175	°C

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-23.





See also *Soldering recommendations.*

Marking code

BZX84-C2V4 = Z11	BZX84-C5V6 = Z3	BZX84-C13 = Y3	BZX84-C33 = Y12
C2V7 = Z12	C6V2 = Z4	C15 = Y4	C36 = Y13
C3V0 = Z13	C6V8 = Z5	C16 = Y5	C39 = Y14
C3V3 = Z14	C7V5 = Z6	C18 = Y6	C43 = Y15
C3V6 = Z15	C8V2 = Z7	C20 = Y7	C47 = Y16
C3V9 = Z16	C9V1 = Z8	C22 = Y8	C51 = Y17
C4V3 = Z17	C10 = Z9	C24 = Y9	C56 = Y18
C4V7 = Z1	C11 = Y1	C27 = Y10	C62 = Y19
C5V1 = Z2	C12 = Y2	C30 = Y11	C68 = Y20
			C75 = Y21

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Repetitive peak forward current	I_{FRM}	max.	250	mA
Repetitive peak working current	I_{ZRM}	max.	250	mA
Total power dissipation up to T_{amb} = 25 °C**	P_{tot}	max.	350	mW
Storage temperature	T_{stg}	−65 to + 175		°C
Junction temperature	T_j	max.	175	°C

THERMAL CHARACTERISTICS*

$T_j = P \times (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\ j\text{-}t}$	=	50	K/W
From tab to soldering points	$R_{th\ t\text{-}s}$	=	280	K/W
From soldering points to ambient**	$R_{th\ s\text{-}a}$	=	90	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Forward voltage I_F = 10 mA		V_F	<	0,9	V
Reverse current					
BZX84-C2V4	V_R = 1 V	I_R	<	50	µA
C2V7	V_R = 1 V	I_R	<	20	µA
C3V0	V_R = 1 V	I_R	<	10	µA
C3V3	V_R = 1 V	I_R	<	5	µA
C3V6	V_R = 1 V	I_R	<	5	µA
C3V9	V_R = 1 V	I_R	<	3	µA
C4V3	V_R = 1 V	I_R	<	3	µA
C4V7	V_R = 2 V	I_R	<	3	µA
C5V1	V_R = 2 V	I_R	<	2	µA
C5V6	V_R = 2 V	I_R	<	1	µA
C6V2	V_R = 4 V	I_R	<	3	µA
C6V8	V_R = 4 V	I_R	<	2	µA
C7V5	V_R = 5 V	I_R	<	1	µA
C8V2	V_R = 5 V	I_R	<	700	nA
C9V1	V_R = 6 V	I_R	<	500	nA
C10	V_R = 7 V	I_R	<	200	nA
C11	V_R = 8 V	I_R	<	100	nA
C12	V_R = 8 V	I_R	<	100	nA
C13	V_R = 8 V	I_R	<	100	nA
C15 to C75	V_R = 0,7 V_{Znom}	I_R	<	50	nA

* See *Thermal characteristics.*

** Device mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

BZX84-....	working voltage V_Z (V) at I_{Ztest} = 5 mA		differential resistance r_{diff} (Ω) at I_{Ztest} = 5 mA		temperature coefficient S_Z (mV/K) at I_{Ztest} = 5 mA			diode capacitance C_d(pF):f = 1 MHz; V_R = 0	
	min.	max.	typ.	max.	min.	typ.	max.	typ.	max.
C2V4	2,2	2,6	70	100	−3,5	−1,6	0	375	450
C2V7	2,5	2,9	75	100	−3,5	−2,0	0	350	450
C3V0	2,8	3,2	80	95	−3,5	−2,1	0	350	450
C3V3	3,1	3,5	85	95	−3,5	−2,4	0	325	450
C3V6	3,4	3,8	85	90	−3,5	−2,4	0	300	450
C3V9	3,7	4,1	85	90	−3,5	−2,5	0	300	450
C4V3	4,0	4,6	80	90	−3,5	−2,5	0	275	450
C4V7	4,4	5,0	50	80	−3,5	−1,4	0,2	245	300
C5V1	4,8	5,4	40	60	−2,7	−0,8	1,2	235	300
C5V6	5,2	6,0	15	40	−2,0	1,2	2,5	225	300
C6V2	5,8	6,6	6	10	0,4	2,3	3,7	125	200
C6V8	6,4	7,2	6	15	1,2	3,0	4,5	105	200
C7V5	7,0	7,9	6	15	2,5	4,0	5,3	95	150
C8V2	7,7	8,7	6	15	3,2	4,6	6,2	90	150
C9V1	8,5	9,6	6	15	3,8	5,5	7,0	70	150
C10	9,4	10,6	8	20	4,5	6,4	8,0	70	90
C11	10,4	11,6	10	20	5,4	7,4	9,0	65	85
C12	11,4	12,7	10	25	6,0	8,4	10,0	65	85
C13	12,4	14,1	10	30	7,0	9,4	11,0	60	80
C15	13,8	15,6	10	30	9,2	11,4	13,0	55	75
C16	15,3	17,1	10	40	10,4	12,4	14,0	52	75
C18	16,8	19,1	10	45	12,4	14,4	16,0	47	70
C20	18,8	21,2	15	55	14,4	16,4	18,0	36	60
C22	20,8	23,3	20	55	16,4	18,4	20,0	34	60
C24	22,8	25,6	25	70	18,4	20,4	22,0	33	55
	at I_Z = 2 mA		at I_Z = 2 mA		at I_Z = 2 mA				
	min.	max.	typ.	max.	min.	typ.	max.	typ.	max.
C27	25,1	28,9	25	80	21,4	23,4	25,3	30	50
C30	28,0	32,0	30	80	24,4	26,6	29,4	27	50
C33	31,0	35,0	35	80	27,4	29,7	33,4	25	45
C36	34,0	38,0	35	90	30,4	33,0	37,4	23	45
C39	37,0	41,0	40	130	33,4	36,4	41,2	21	45
C43	40,0	46,0	45	150	37,6	41,2	46,6	21	40
C47	44,0	50,0	50	170	42,0	46,1	51,8	19	40
C51	48,0	54,0	60	180	46,6	51,0	57,2	19	40
C56	52,0	60,0	70	200	52,2	57,0	63,8	18	40
C62	58,0	66,0	80	215	58,8	64,4	71,6	17	35
C68	64,0	72,0	90	240	65,6	71,7	79,8	17	35
C75	70,0	79,0	95	255	73,4	80,2	88,6	16,5	35

BZX84-....	working voltage V_Z (V) at I_Z = 1 mA			differential resistance r_{diff} (Ω) at I_Z = 1 mA		working voltage V_Z (V) at I_Z = 20 mA			differential resistance r_{diff} (Ω) at I_Z = 20 mA	
	min.	nom.	max.	typ.	max.	min.	nom.	max.	typ.	max.
C2V4	1,7	1,9	2,1	275	600	2,6	2,9	3,2	25	50
C2V7	1,9	2,2	2,4	300	600	3,0	3,3	3,6	25	50
C3V0	2,1	2,4	2,7	325	600	3,3	3,6	3,9	25	50
C3V3	2,3	2,6	2,9	350	600	3,6	3,9	4,2	20	40
C3V6	2,7	3,0	3,3	375	600	3,9	4,2	4,5	20	40
C3V9	2,9	3,2	3,5	400	600	4,1	4,4	4,7	15	30
C4V3	3,3	3,6	4,0	410	600	4,4	4,7	5,1	15	30
C4V7	3,7	4,2	4,7	425	500	4,5	5,0	5,4	8	15
C5V1	4,2	4,7	5,3	400	480	5,0	5,4	5,9	6	15
C5V6	4,8	5,4	6,0	80	400	5,2	5,7	6,3	4	10
C6V2	5,6	6,1	6,6	40	150	5,8	6,3	6,8	3	6
C6V8	6,3	6,7	7,2	30	80	6,4	6,9	7,4	2,5	6
C7V5	6,9	7,4	7,9	30	80	7,0	7,6	8,0	2,5	6
C8V2	7,6	8,1	8,7	40	80	7,7	8,3	8,8	3	6
C9V1	8,4	9,0	9,6	40	100	8,5	9,2	9,7	4	8
C10	9,3	9,9	10,6	50	150	9,4	10,1	10,7	4	10
C11	10,2	10,9	11,6	50	150	10,4	11,1	11,8	5	10
C12	11,2	11,9	12,7	50	150	11,4	12,1	12,9	5	10
C13	12,3	12,9	14,0	50	170	12,5	13,1	14,2	5	15
C15	13,7	14,9	15,5	50	200	13,9	15,1	15,7	6	20
C16	15,2	15,9	17,0	50	200	15,4	16,1	17,2	6	20
C18	16,7	17,9	19,0	50	225	16,9	18,1	19,2	6	20
C20	18,7	19,9	21,1	60	225	18,9	20,1	21,4	7	20
C22	20,7	21,9	23,2	60	250	20,9	22,1	23,4	7	25
C24	22,7	23,9	25,5	60	250	22,9	24,1	25,7	7	25
	at I_Z = 0,1 mA			at I_Z = 0,5 mA		at I_Z = 10 mA			at I_Z = 10 mA	
	min.	nom.	max.	typ.	max.	min.	nom.	max.	typ.	max.
C27	25,0	26,9	28,9	65	300	25,2	27,1	29,3	10	45
C30	27,8	29,9	32,0	70	300	28,1	30,1	32,4	15	50
C33	30,8	32,9	35,0	75	325	31,1	33,1	35,4	20	55
C36	33,8	35,9	38,0	80	350	34,1	36,1	38,4	25	60
C39	36,7	38,9	41,0	80	350	37,1	39,1	41,5	25	70
C43	39,7	42,9	46,0	85	375	40,1	43,1	46,5	25	80
C47	43,7	46,8	50,0	85	375	44,1	47,1	50,5	30	90
C51	47,6	50,8	54,0	90	400	48,1	51,1	54,6	35	100
C56	51,5	55,7	60,0	100	425	52,1	56,1	60,8	45	110
C62	57,4	61,7	66,0	120	450	58,2	62,1	67,0	60	120
C68	63,4	67,7	72,0	150	475	64,2	68,2	73,2	75	130
C75	69,4	74,7	79,0	170	500	70,3	75,3	80,2	90	140

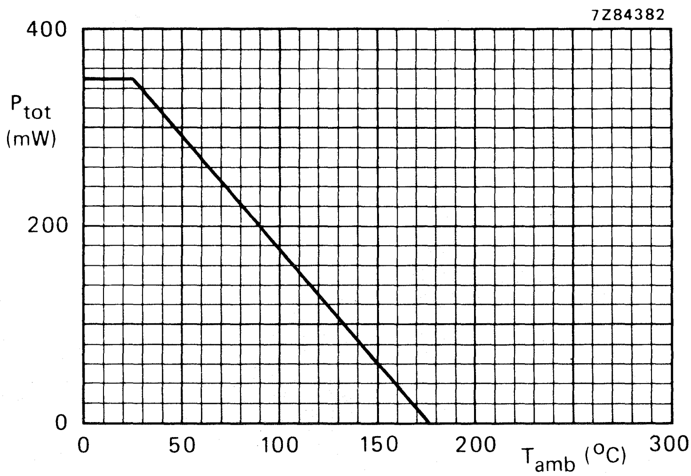


Fig. 2 Power derating curve.

Model for calculating the static working voltage ($V_{Z\ stat}$).

This model can be derived from $V_{Z\ stat} = V_{Z\ dyn} + \Delta V_Z$ of which $V_{Z\ dyn}$ is given in the preceding tables and can be derived from the typical dynamic characteristic curves in Figs 3 to 6.
$\Delta V_Z = \Delta T \times S_Z$. For S_Z see tables and graphs S_Z versus T_j.
$\Delta T = P_{tot} \times R_{th\ j\text{-}a} = I_Z \times V_{Z\ dyn} \times R_{th\ j\text{-}a}$.
Following $\Delta V_Z = I_Z \times V_{Z\ dyn} \times R_{th\ j\text{-}a} \times S_Z$ and the model will be:

$$V_{Z\ stat} = V_{Z\ dyn} + I_Z \times V_{Z\ dyn} \times R_{th\ j\text{-}a} \times S_Z$$

Calculating example

BZX84-C24 mounted on a ceramic substrate of 7 x 5 x 0,6 mm; at I_Z = 7 mA.

$$V_{Z\ stat} = 24 + (\frac{7}{1000} \times 24 \times \frac{430}{1000} \times 20,3)$$
$$= 24 + 1,47 = 25,47\ V.$$

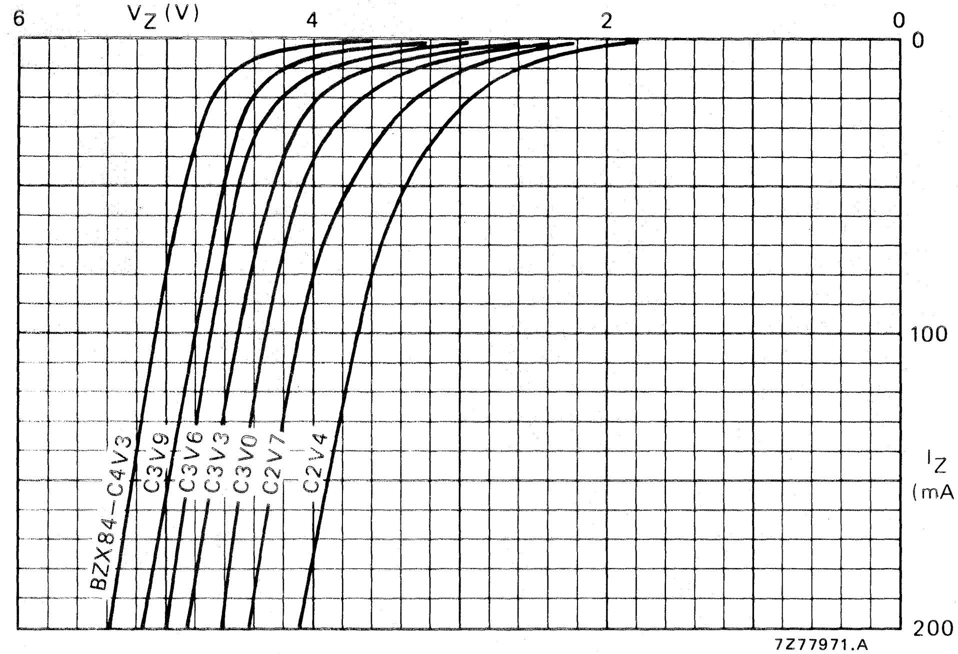


Fig. 3 Dynamic characteristics; typical values; T_j = 25 °C.

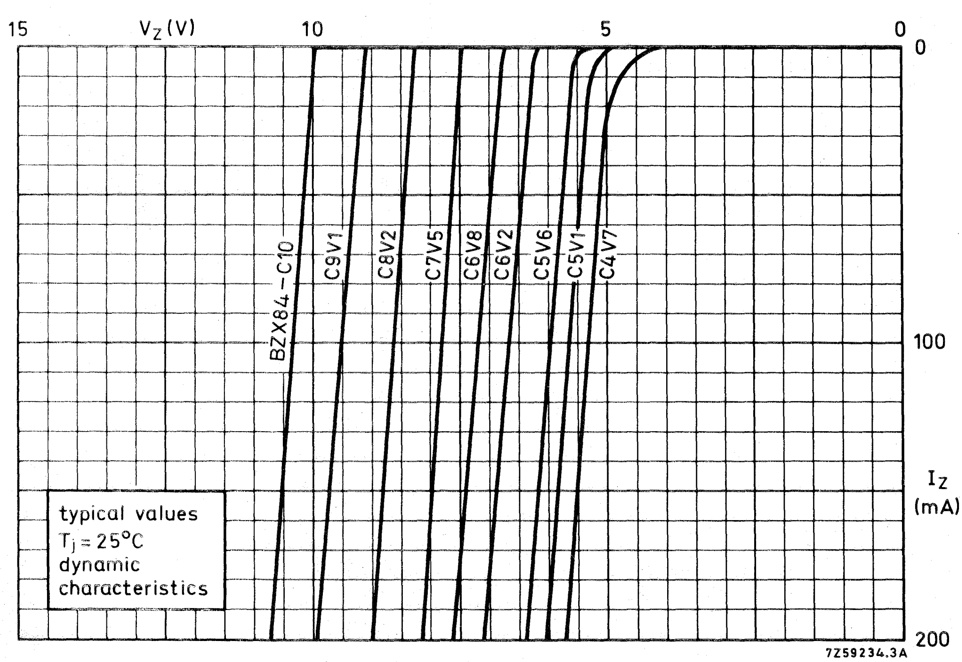


Fig. 4 Dynamic characteristics; typical values; T_j = 25 °C.

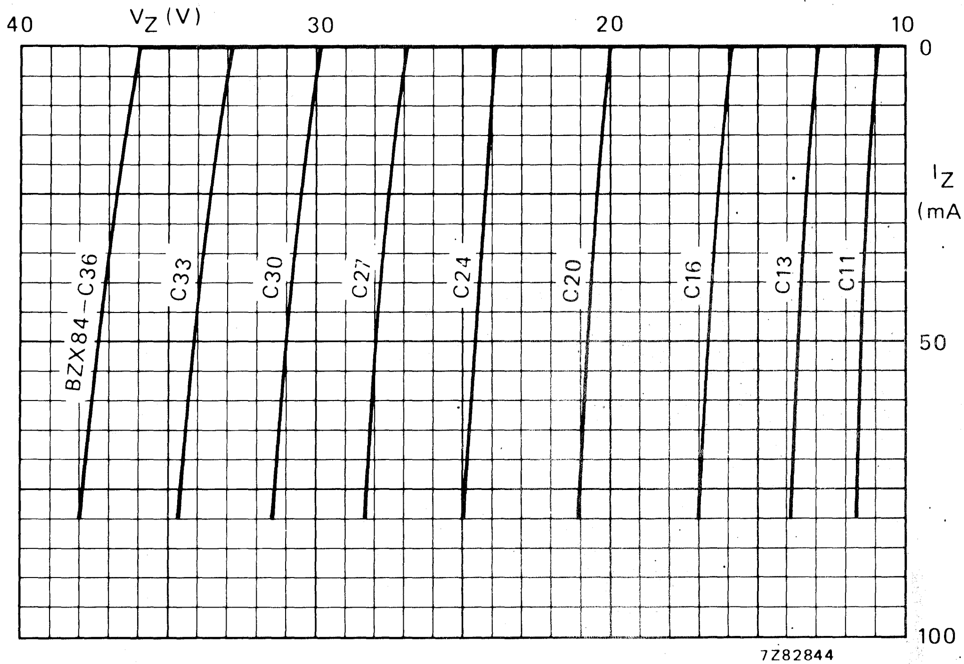


Fig. 5 Dynamic characteristics; typical values; T_j = 25 °C.

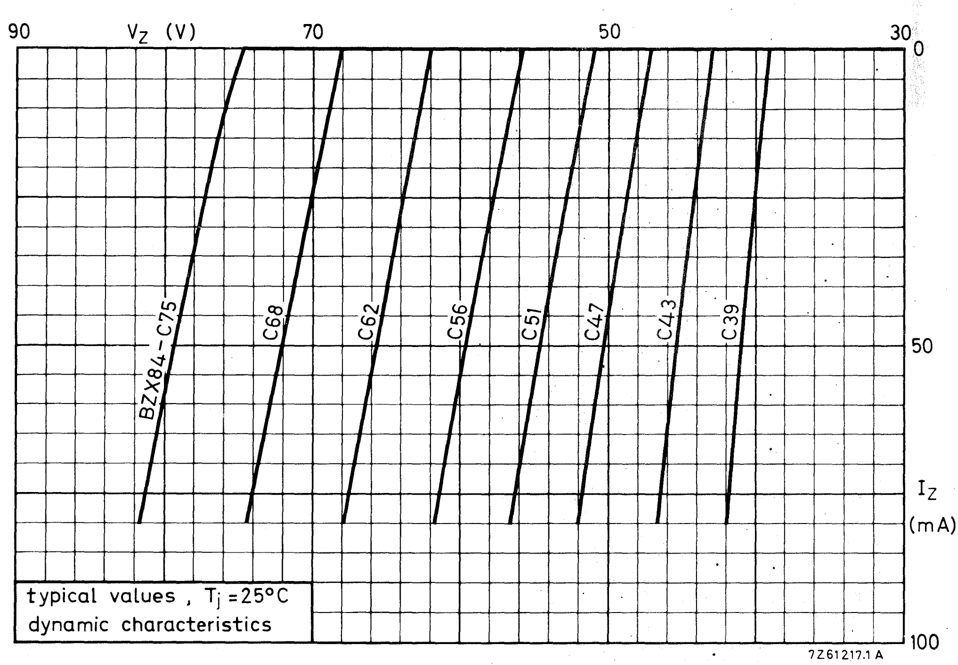


Fig. 6 Dynamic characteristics; typical values; T_j = 25 °C.

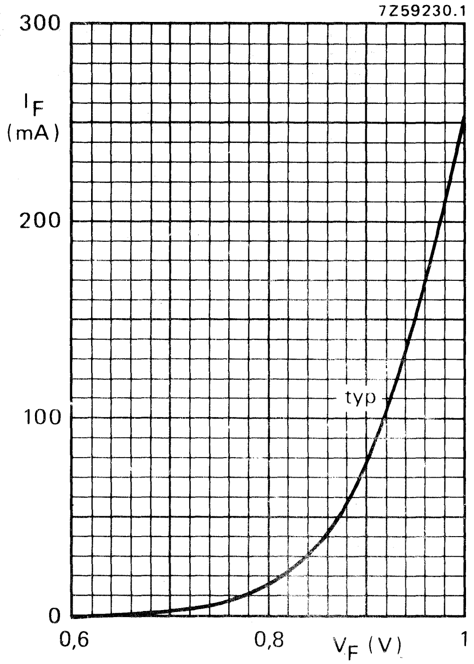


Fig. 7 Typical values at T_j = 25 °C.

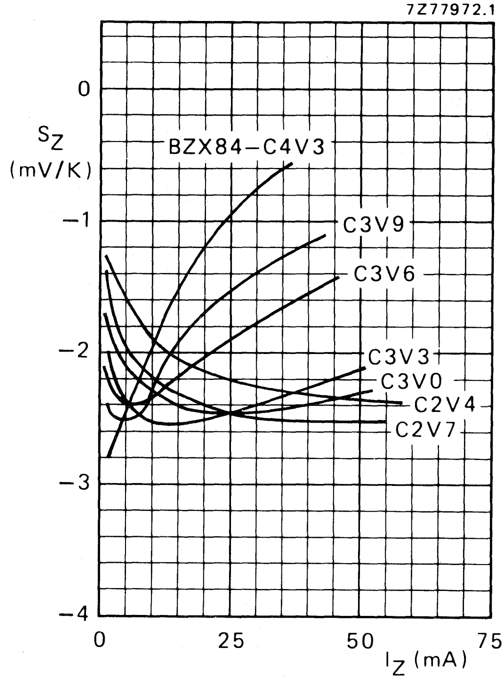


Fig. 8 Typical values; T_j = 25 to 175 °C.

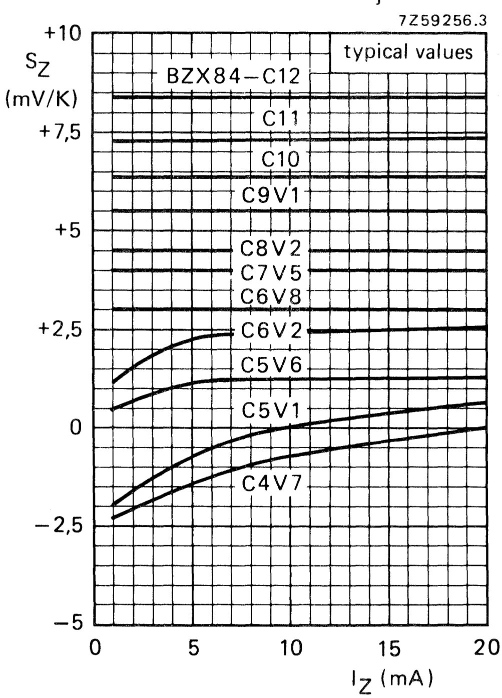


Fig. 9 Typical values; T_j = 25 to 175 °C.

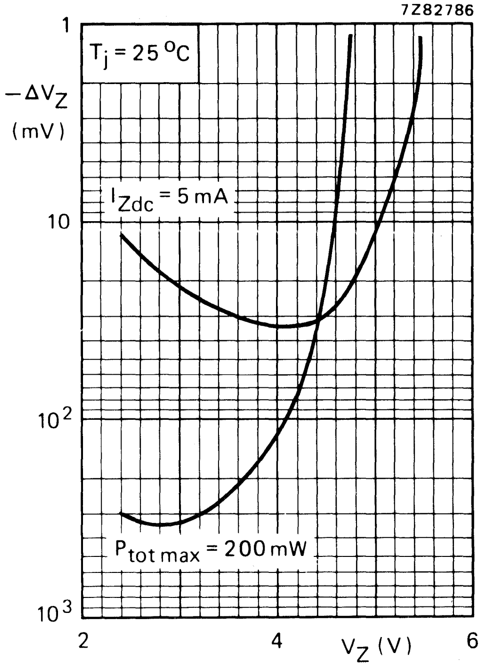


Fig. 10.

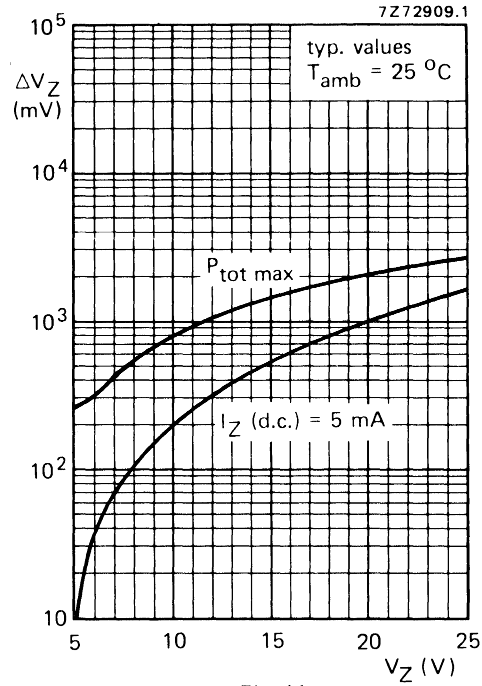


Fig. 11.

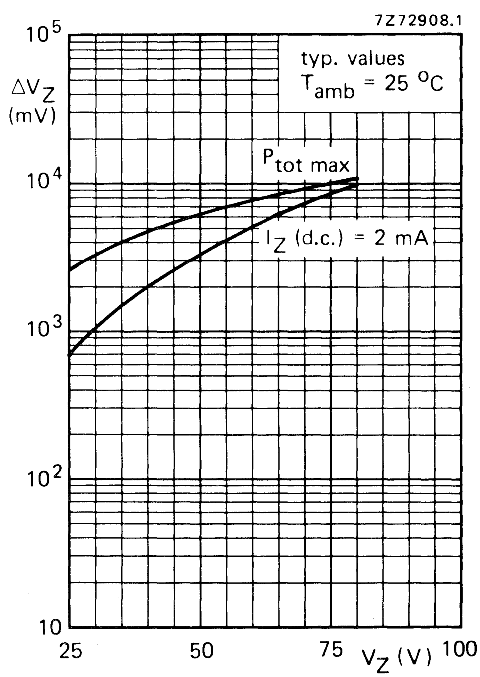


Fig. 12.

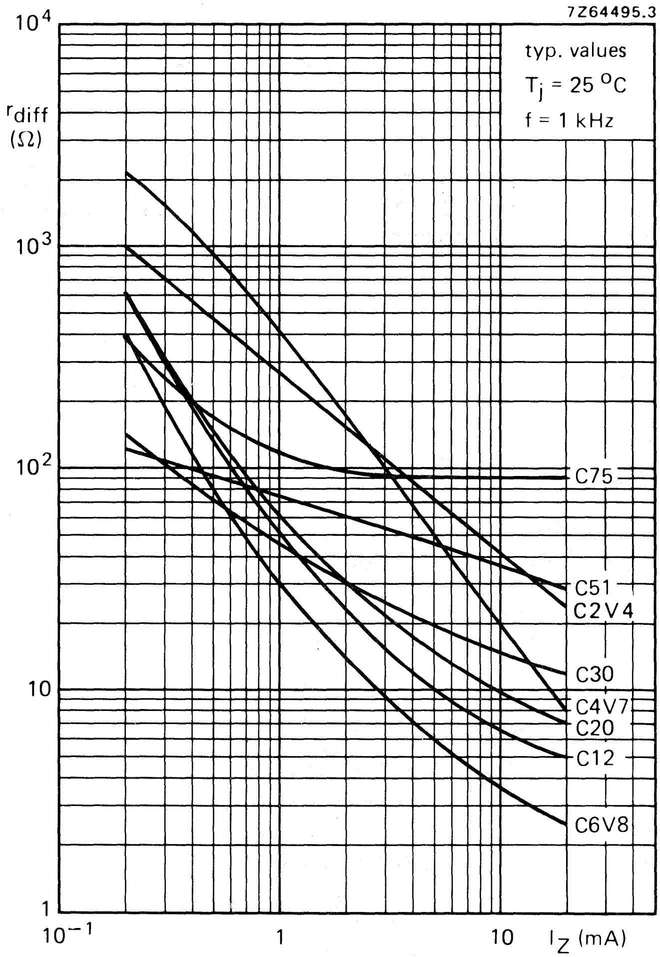

7Z64495.3
typ. values
T_j = 25 °C
f = 1 kHz
r_{diff} (Ω)
10^4
10^3
10^2
10
1
10^{-1}
1
10
I_Z (mA)
C75
C51
C2V4
C30
C4V7
C20
C12
C6V8

Fig. 13.

N-CHANNEL FETS

Silicon n-channel depletion type junction field-effect transistors on a plastic microminiature envelope intended for application in thick and thin-film circuits. The transistors are intended for low-power, chopper or switching applications in industry.

QUICK REFERENCE DATA

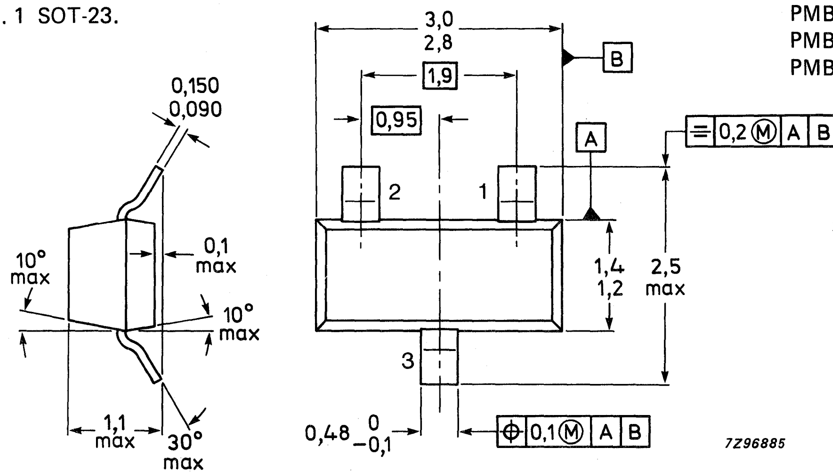
			PMBF4391	PMBF4392	PMBF4393	
Drain-source voltage	$\pm V_{DS}$	max.	40	40	40	V
Drain current V_{DS} = 20 V; V_{GS} = 0	I_{DSS}	>	50	25	5	mA
Gate-source cut-off voltage V_{DS} = 20 V; I_D = 1 nA	$-V_{(P)GS}$	> <	4 10	2 5	0,5 3	V V
Drain-source resistance (on) at f = 1 kHz I_D = 1 mA; V_{GS} = 0	$r_{ds\,on}$	<	30	60	100	Ω
Feedback capacitance at f = 1 MHz $-V_{GS}$ = 12 V; V_{DS} = 0	C_{rs}	<	3,5	3,5	3,5	pF
Turn-off time V_{DD} = 10 V; V_{GS} = 0						
I_D = 12 mA; $-V_{GSM}$ = 12 V	t_{off}	<	20	—	—	ns
I_D = 6 mA; $-V_{GSM}$ = 7 V	t_{off}	<	—	35	—	ns
I_D = 3 mA; $-V_{GSM}$ = 5 V	t_{off}	<	—	—	50	ns

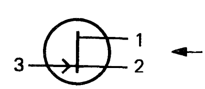
MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-23.

Marking code
PMBF4391 = M62
PMBF4392 = M63
PMBF4393 = M64





TOP VIEW

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Drain-source voltage (See Fig. 4)	$\pm V_{DS}$	max.	40 V
Drain-gate voltage (See Fig. 4)	V_{DGO}	max.	40 V
Gate-source voltage (See Fig. 4)	$-V_{GSO}$	max.	40 V
Gate current (d.c.)	I_G	max.	50 mA
Total power dissipation up to T_{amb} = 65 °C	P_{tot}	max.	250 mW
Storage temperature range	T_{stg}	−65 to + 175 °C	
Junction temperature	T_j	max.	175 °C

THERMAL CHARACTERISTICS

$T_j = P\,(R_{th\,j\text{-}t} + R_{th\,t\text{-}s} + R_{th\,s\text{-}a}) + T_{amb}$

Thermal resistance

From junction to tab	$R_{th\,j\text{-}t}$	=	60 K/W
From tab to soldering points	$R_{th\,t\text{-}s}$	=	260 K/W
From soldering points to ambient *	$R_{th\,s\text{-}a}$	=	120 K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Gate-source voltage			
I_G = 1 mA; V_{DS} = 0	V_{GSon}	<	1 V
Gate-source cut-off current			
V_{DS} = 0 V; $-V_{GS}$ = 20 V	$-I_{GSS}$	<	1 nA
V_{DS} = 0 V; $-V_{GS}$ = 20 V; T_{amb} = 150 °C	$-I_{GSS}$	<	0,2 μA

			PMBF4391	PMBF4392	PMBF4393
Drain current**					
V_{DS} = 20 V; V_{GS} = 0	I_{DSS}	>	50	25	5 mA
		<	150	75	30 mA
Gate-source breakdown voltage					
$-I_G$ = 1 μA; V_{DS} = 0	$-V_{(BR)GSS}$	>	40	40	40 V
Gate-source cut-off voltage					
I_D = 1 nA; V_{DS} = 20 V	$-V_{(P)GS}$	>	4	2	0,5 V
		<	10	5	3 V
Drain-source voltage (on)					
I_D = 12 mA; V_{GS} = 0	V_{DSon}	<	0,4	–	– V
I_D = 6 mA; V_{GS} = 0	V_{DSon}	<		0,4	– V
I_D = 3 mA; V_{GS} = 0	V_{DSon}	<	–	–	0,4 V
Drain-source resistance (on)					
I_D = 0; V_{GS} = 0; f = 1 kHz	$r_{ds\,on}$	<	30	60	100 Ω

→ * Mounted on a ceramic substrate of 7 mm x 5 mm x 0,7 mm.
** Measured under pulsed conditions; t_p = 100 μs; δ = 0,01.

			PMBF4391	PMBF4392	PMBF4393
Drain cut-off current					
$-V_{GS}$ = 12 V; V_{DS} = 20 V	I_{DSX}	<	1	–	– nA
$-V_{GS}$ = 7 V; V_{DS} = 20 V	I_{DSX}	<	–	1	– nA
$-V_{GS}$ = 5 V; V_{DS} = 20 V	I_{DSX}	<	–	–	1 nA
$-V_{GS}$ = 12 V; V_{DS} = 20 V; T_{amb} = 150 °C	I_{DSX}	<	0,2	–	– μA
$-V_{GS}$ = 7 V; V_{DS} = 20 V; T_{amb} = 150 °C	I_{DSX}	<	–	0,2	– μA
$-V_{GS}$ = 5 V; V_{DS} = 20 V; T_{amb} = 150 °C	I_{DSX}	<	–	–	0,2 μA
y-parameters (common source) V_{DS} = 20 V; V_{GS} = 0; f = 1 MHz					
Input capacitance	C_{is}	<	14	14	14 pF
Feedback capacitance	C_{rs}	<	3,5	3,5	3,5 pF
Switching times V_{DD} = 10 V; V_{GS} = 0					
Conditions I_D and $-V_{GSM}$	I_D	=	12	6	3 mA
	$-V_{GSM}$	=	12	7	5 V
Rise time	t_r	<	5	5	5 ns
Turn on time	t_{on}	<	15	15	15 ns
Fall time	t_f	<	15	20	30 ns
Turn off time	t_{off}	<	20	35	50 ns

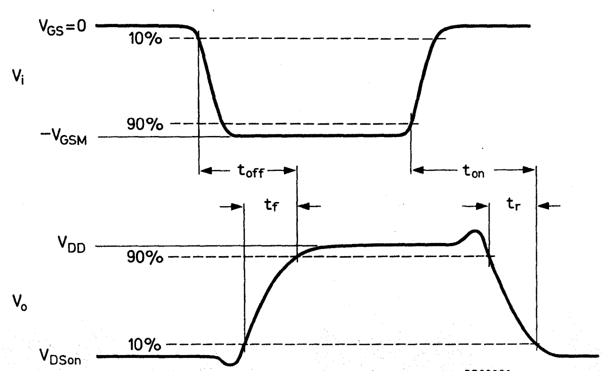
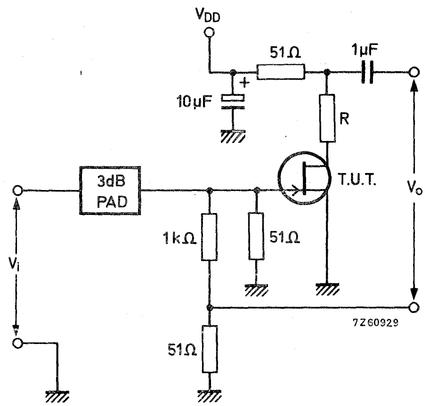


Fig. 2 Switching times waveforms.



$R = \frac{9,6}{I_D} - 51\ \Omega$

Pulse generator:

t_r	$<$	0,5 ns
t_f	$<$	0,5 ns
t_p	=	100 μs
δ	=	0,01

Oscilloscope:

R_i = 50 Ω

Fig. 3 Test circuit.

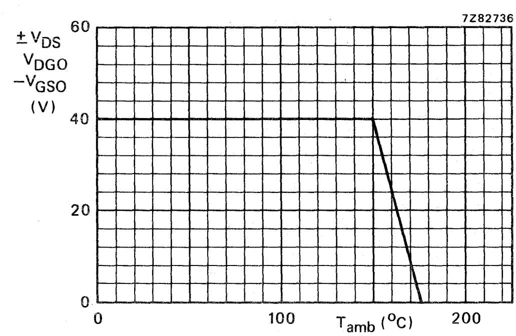


Fig. 4 Voltage derating curve.

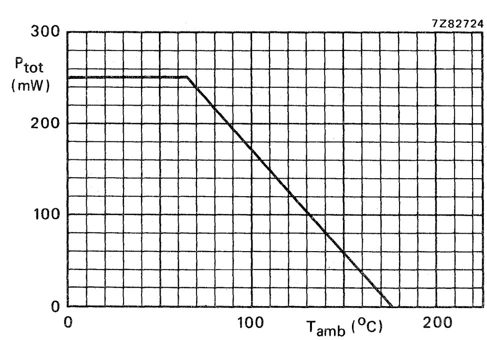


Fig. 5 Power derating curve.

SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N silicon transistors, in a microminiature plastic envelope intended for switching and linear applications in thick and thin-film circuits.

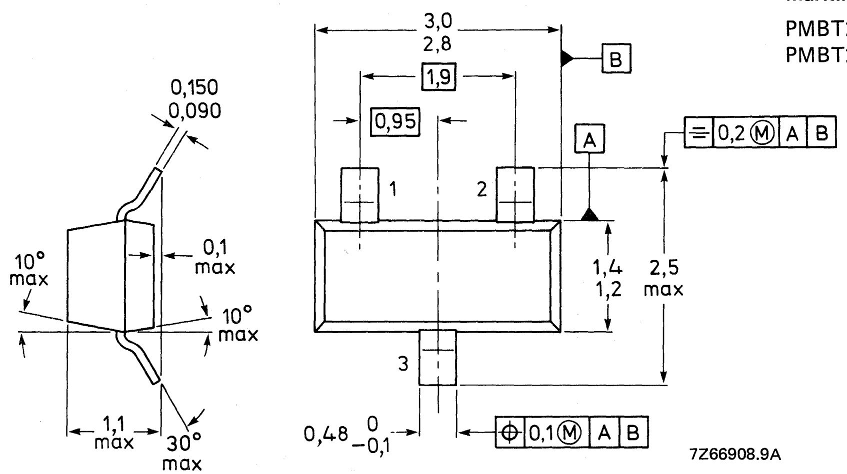
QUICK REFERENCE DATA

			PMBT2222	PMBT2222A	
Collector-base voltage (open emitter)	V_{CBO}	max.	60	75	V
Collector-emitter voltage (open base)	V_{CEO}	max.	30	40	V
Emitter-base voltage (open collector)	V_{EBO}	max.	5,0	6,0	V
Collector current (d.c.)	I_C	max.	600		mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	350		mW
D.C. current gain					
I_C = 150 mA; V_{CE} = 10 V	h_{FE}		100 to 300		
I_C = 500 mA; V_{CE} = 10 V	h_{FE}	>	30	40	
Transition frequency at f = 100 MHz					
I_C = 20 mA; V_{CE} = 20 V	f_T	>	250	300	MHz

MECHANICAL DATA

Dimensions in mm

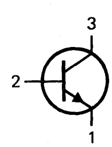
Fig. 1 SOT-23.



TOP VIEW

Marking code

PMBT2222 = P1B
PMBT2222A = P1P



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			PMBT2222	PMBT2222A	
Collector-base voltage (open emitter) see Fig. 4	V_{CBO}	max.	60	75	V
Collector-emitter voltage (open base) see Fig. 4	V_{CEO}	max.	30	40	V
Emitter-base voltage (open collector) see Fig. 4	V_{EBO}	max.	5,0	6,0	V
Collector current (d.c.)	I_C	max.	600		mA
Total power dissipation* up to T_{amb} = 25 °C	P_{tot}	max.	350		mW
Storage temperature range	T_{stg}		−55 to 150		°C
Junction temperature	T_j	max.	150		°C

THERMAL RESISTANCE *

From junction to ambient	$R_{th\ j\text{-}a}$	=	350	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			PMBT2222	PMBT2222A	
Collector cut-off current					
$I_E = 0$; $V_{CB} = 50$ V	I_{CBO}	<	0,01	–	μA
$I_E = 0$; $V_{CB} = 60$ V	I_{CBO}	<	–	0,01	μA
$I_E = 0$; $V_{CB} = 50$ V; $T_j = 125$ °C	I_{CBO}	<	10	–	μA
$I_E = 0$; $V_{CB} = 60$ V; $T_j = 125$ °C	I_{CBO}	<	–	10	μA
$V_{EB} = 3$ V; $V_{CE} = 60$ V	I_{CEX}	<	–	10	nA
Base current with reverse biased emitter junction					
$V_{EB} = 3$ V; $V_{CE} = 60$ V	I_{BEX}	<	–	20	nA
Emitter cut-off current					
$I_C = 0$; $V_{EB} = 3$ V	I_{EBO}	<		10	nA
Saturation voltages**					
$I_C = 150$ mA; $I_B = 15$ mA	V_{CEsat}	<	400	300	mV
	V_{BEsat}	<	1300	–	mV
	V_{BEsat}		–	0,6 to 1,2	V
$I_C = 500$ mA; $I_B = 50$ mA	V_{CEsat}	<	1600	1000	mV
	V_{BEsat}	<	2600	2000	mV
Breakdown voltages					
$I_C = 1,0$ mA; $I_B = 0$	$V_{(BR)CEO}$	>	30	40	V
$I_C = 100$ μA; $I_E = 0$	$V_{(BR)CBO}$	>	60	75	V
$I_C = 0$; $I_E = 10$ μA	$V_{(BR)EBO}$	>	5,0	6,0	V

* Device mounted on a ceramic substrate of 15 mm x 15 mm x 0,7 mm.
** Measured under pulsed conditions to avoid excessive dissipation; $t_p \leq 300$ μs; $\delta \leq 0,02$.

			PMBT2222	PMBT2222A	
D.C. current gain					
I_C = 0,1 mA; V_{CE} = 10 V	h_{FE}	>	35		
I_C = 1 mA; V_{CE} = 10 V	h_{FE}	>	50		
I_C = 10 mA; V_{CE} = 10 V	h_{FE}	>	75		
I_C = 10 mA; V_{CE} = 10 V; T_{amb} = −55 °C	h_{FE}	>	35		
I_C = 150 mA; V_{CE} = 10 V	h_{FE}		100 to 300		
I_C = 150 mA; V_{CE} = 1 V	h_{FE}	>	50		
I_C = 500 mA; V_{CE} = 10 V	h_{FE}	>	30	40	
Transition frequency at f = 100 MHz*					
I_C = 20 mA; V_{CE} = 20 V	f_T	>	250	300	MHz
Output capacitance at f = 1 MHz					
I_E = 0; V_{CB} = 10 V	C_o	<	8,0		pF
Input capacitance at f = 1 MHz					
I_C = 0; V_{EB} = 0,5 V	C_i	<	30	25	
h-parameters (common emitter) at f = 1 kHz					
I_C = 1 mA; V_{CE} = 10 V					
input impedance	h_{ie}		2,0 to 8,0		kΩ
reverse voltage transfer ratio	h_{re}		$< 8,0 \times 10^{-4}$		
small signal current gain	h_{fe}		50 to 300		
output admittance	h_{oe}		5,0 to 35		μS
I_C = 10 mA; V_{CE} = 10 V					
input impedance	h_{ie}		0,25 to 1,25		kΩ
reverse voltage transfer ratio	h_{re}		$< 4,0 \times 10^{-4}$		
small signal current gain	h_{fe}		75 to 375		
output admittance	h_{oe}		25 to 200		μS
Noise figure at R_S = 1 kΩ					
I_C = 100 μA; V_{CE} = 10 V; f = 1 kHz	F		4,0		dB
Switching times (between 10% and 90% levels)					
Turn-on time switched to I_C = 150 mA					
delay time	t_d	<	10		ns
rise time	t_r	<	25		ns
Turn-off time switched from I_C = 150 mA					
storage time	t_s	<	225		ns
fall time	t_f	<	60		ns

* f_T is defined as the frequency at which h_{fe} extrapolates to unity.

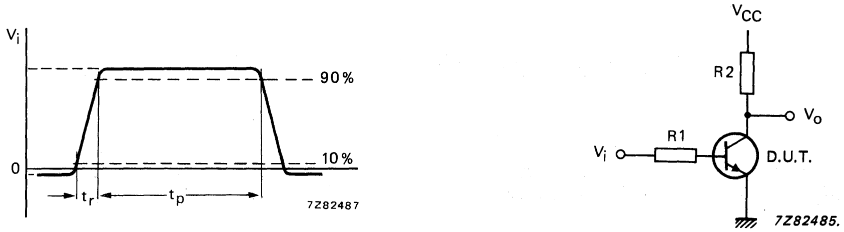


Fig. 2 Waveform and test circuit delay and rise time.

V_i = –0,5 to + 9,9 V; V_{CC} = 30 V; R1 = 619 Ω; R2 = 200 Ω.

Pulse generator:				Oscilloscope:			
pulse duration	t_p	$\leqslant$	200 ns	input impedance	Z_i	>	100 kΩ
rise time	t_r	$\leqslant$	2 ns	input capacitance	C_i	<	12 pF
duty factor	δ	=	2 %	rise time	t_r	<	5 ns

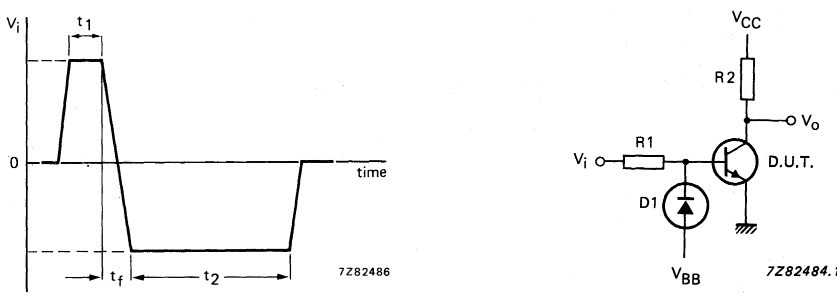


Fig. 3 Waveform and test circuit storage and fall time.

V_i = –13,8 to + 16,2 V; V_{CC} = 30 V; $-V_{BB}$ = 3 V; R1 = 1 kΩ; R2 = 200 Ω.

Pulse generator:				Oscilloscope:			
fall time	t_f	<	5 ns	input impedance	Z_i	>	100 kΩ
pulse time	t_1	=	100 μs	input capacitance	C_i	<	12 pF
	t_2	=	500 μs	rise time	t_r	<	5 ns

SILICON PLANAR EPITAXIAL TRANSISTORS

P-N-P silicon transistors, in a microminiature plastic envelope, intended for medium power switching and general purpose amplifier applications in thick and thin-film circuits.

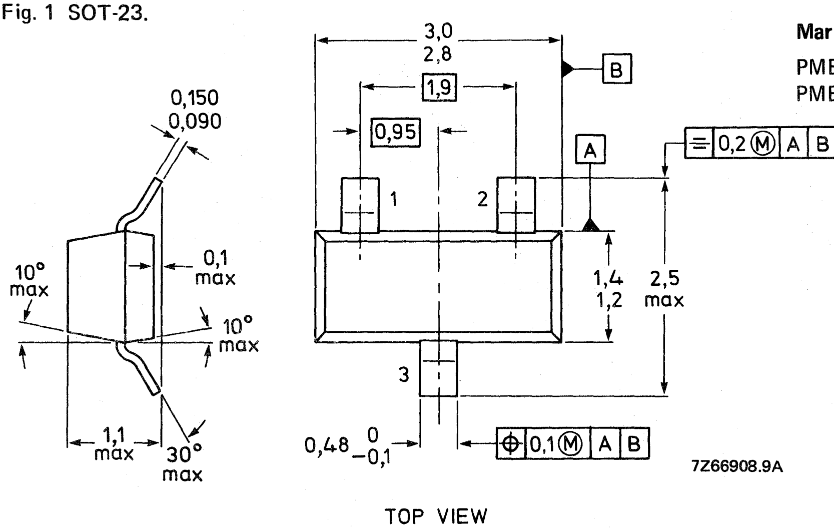
QUICK REFERENCE DATA

			PMBT2907	PMBT2907A	
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	60	60	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	40	60	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5,0		V
Collector current (d.c.)	$-I_C$	max.	600		mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	350		mW
Junction temperature	T_j	max.	150		°C
D.C. current gain $-I_C$ = 500 mA; $-V_{CE}$ = 10 V	h_{FE}	>	30	50	
Turn-off switching time $-I_{Con}$ = 150 mA; $-I_{Bon}$ = I_{Boff} = 15 mA	t_{off}	<	100		ns
Transition frequency at f = 100 MHz $-I_C$ = 50 mA; $-V_{CE}$ = 20 V	f_T	>	200		MHz

MECHANICAL DATA

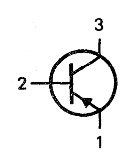
Dimensions in mm

Fig. 1 SOT-23.



Marking code

PMBT2907 = P2B
PMBT2907A = P2F



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			PMBT2907	PMBT2907A	
Collector-base voltage (open emitter) see Figs 4 and 5	$-V_{CBO}$	max.	60	60	V
Collector-emitter voltage (open base) see Figs 4 and 5	$-V_{CEO}$	max.	40	60	V
Emitter-base voltage (open collector) see Figs 4 and 5	$-V_{EBO}$	max.	5,0		V
Collector current (d.c.)	$-I_C$	max.	600		mA
Power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	350		mW
Storage temperature range	T_{stg}		−65 to +150		°C
Junction temperature	T_j	max.	150		°C

THERMAL RESISTANCE *

From junction to ambient in free air	$R_{th\ j\text{-}a}$	=	350	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

			PMBT2907	PMBT2907A	
Collector cut-off current					
$I_E = 0$; $-V_{CB} = 50$ V	$-I_{CBO}$	<	20	10	nA
$I_E = 0$; $-V_{CB} = 50$ V; $T_j = 125$ °C	$-I_{CBO}$	<	20	10	μA
$-V_{EB} = 0{,}5$ V; $-V_{CE} = 30$ V	$-I_{CEX}$	<	50		nA
Base current with reverse biased emitter junction					
$-V_{EB} = 3$ V; $-V_{CE} = 30$ V	$-I_{BEX}$	<	50		nA
Saturation voltages**					
$-I_C = 150$ mA; $-I_B = 15$ mA	$-V_{CEsat}$	<	0,4		V
	$-V_{BEsat}$	<	1,3		V
$-I_C = 500$ mA; $-I_B = 50$ mA	$-V_{CEsat}$	<	1,6		V
	$-V_{BEsat}$	<	2,6		V
Collector-base breakdown voltage open emitter; $-I_C = 10$ μA; $I_E = 0$	$-V_{(BR)CBO}$		60		V
Collector-emitter breakdown voltage open base; $-I_C = 10$ mA; $I_B = 0$	$-V_{(BR)CEO}$	>	40	60	V
Emitter-base breakdown voltage open collector; $-I_E = 10$ μA; $I_C = 0$	$-V_{(BR)EBO}$		5,0		V

* Device mounted on a ceramic substrate of 15 mm x 15 mm x 0,7 mm.

			PMBT2907	PMBT2907A	
D.C. current gain					
$-I_C = 0{,}1$ mA; $-V_{CE} = 10$ V	h_{FE}	>	35	75	
$-I_C = 1$ mA; $-V_{CE} = 10$ V	h_{FE}	>	50	100	
$-I_C = 10$ mA; $-V_{CE} = 10$ V	h_{FE}	>	75	100	
$-I_C = 150$ mA; $-V_{CE} = 10$ V	h_{FE}		100 to 300		
$-I_C = 500$ mA; $-V_{CE} = 10$ V	h_{FE}	>	30	50	
Transition frequency at f = 100 MHz					
$-I_C = 50$ mA; $-V_{CE} = 20$ V; $T_{amb} = 25$ °C	f_T	>	200		MHz
Output capacitance at f = 1 MHz					
$I_E = I_e = 0$; $-V_{CB} = 10$ V	C_o	<	8,0		pF
Input capacitance at f = 1 MHz					
$I_C = I_c = 0$; $-V_{EB} = 2$ V	C_i	<	30		pF

Switching times (between 10% and 90% levels)

Turn-on time when switched to				
$-I_C = 150$ mA; $-I_B = 15$ mA; $V_{CC} = 30$ V				
delay time	t_d	<	10	ns
rise time	t_r	<	40	ns
turn-on time ($t_d + t_r$)	t_{on}	<	45	ns
Turn-off time when switched from				
$-I_C = 150$ mA; $-I_B = 15$ mA; $V_{CC} = 6$ V				
to cut-off with $+I_{BM} = 15$ mA (see Fig. 3)				
storage time	t_s	<	80	ns
fall time	t_f	<	30	ns
turn-off time ($t_s + t_f$)	t_{off}	<	100	ns

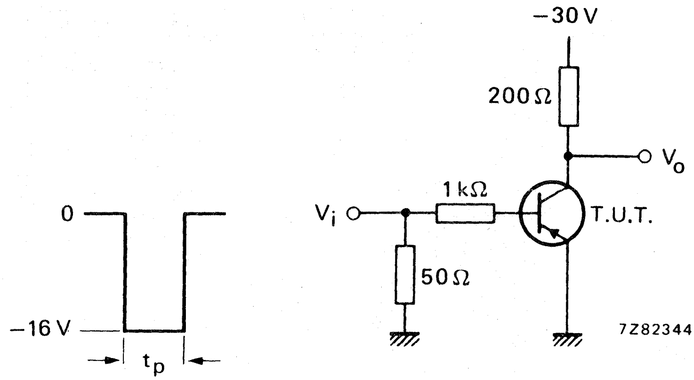


Fig. 2 Turn-on switching time test circuit.

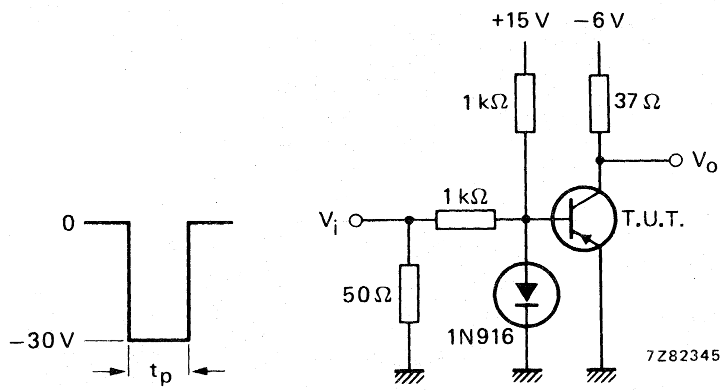


Fig. 3 Turn-off switching time test circuit.

Input pulse generator: Fig. 2 and Fig. 3	frequency	f	=	150	Hz
	pulse duration	t_p	=	200	ns
	rise time	t_r	$\leqslant$	2	ns
	output impedance	Z_o	=	50	Ω
Output oscilloscope: Fig. 2 and Fig. 3	rise time	t_r	$\leqslant$	5	ns
	input impedance	Z_i	=	10	MΩ

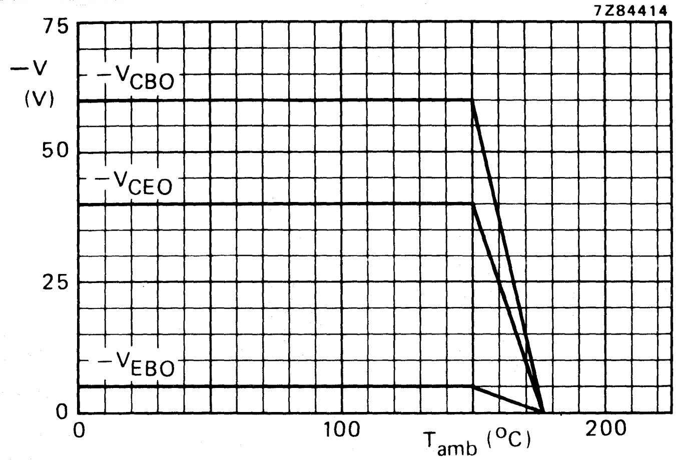


Fig. 4 Voltage derating curves PMBT2907.

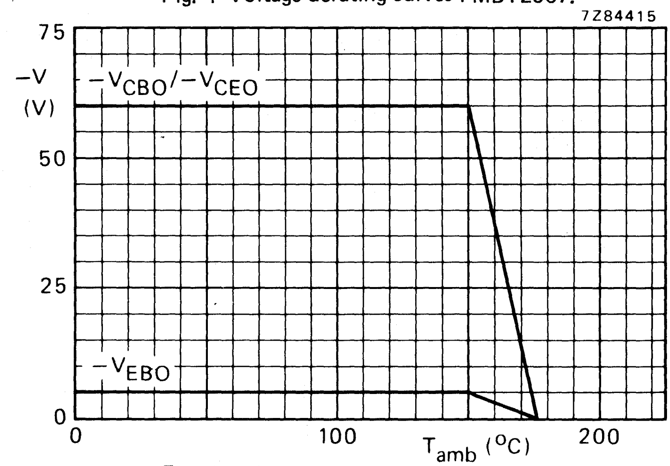


Fig. 5 Voltage derating curves PMBT2907A.

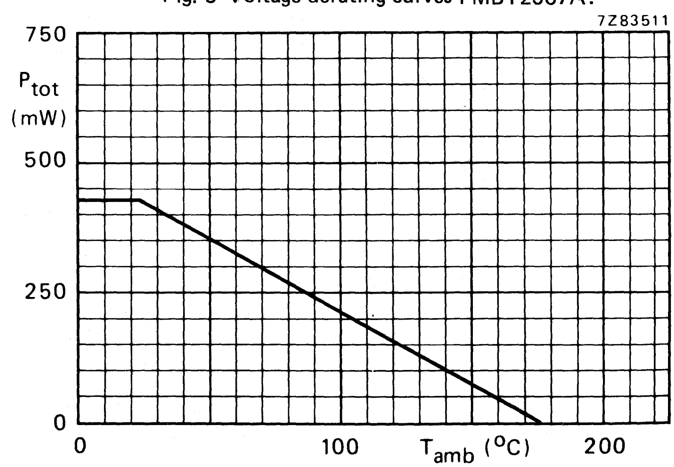


Fig. 6 Power derating curve PMBT2907/A.

SILICON EPITAXIAL TRANSISTORS

N-P-N transistors in a microminiature (SMD) plastic envelope intended for surface mounted applications. They are primarily intended for use in telephony and professional communication equipment.

QUICK REFERENCE DATA

			PMBT3903	PMBT3904	
Collector-base voltage (open emitter)	V_{CBO}	max.	60		V
Collector-emitter voltage (open base)	V_{CEO}	max.	40		V
Emitter-base voltage (open collector)	V_{EBO}	max.	6		V
Collector current (d.c.)	I_C	max.	200		mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300		mW
D.C. current gain I_C = 10 mA; V_{CE} = 1 V	h_{FE}	>	50	100	
		<	150	300	
Transition frequency at f = 35 MHz I_C = 10 mA; V_{CE} = 20 V	f_T	>	250	300	MHz

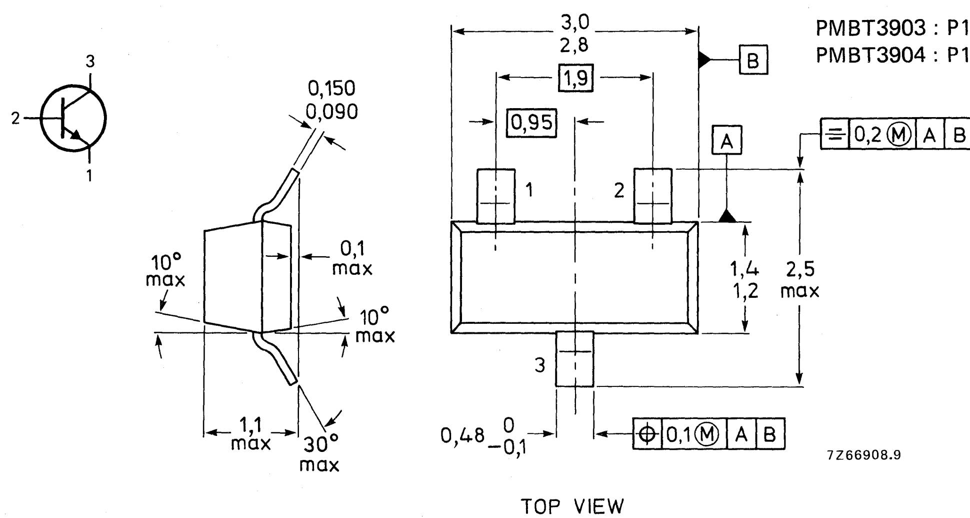
MECHANICAL DATA

Fig. 1 SOT-23.

Dimensions in mm

Marking code

PMBT3903 : P1Y
PMBT3904 : P1A



See also Soldering recommendations.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	V_{CBO}	max.	60	V
Collector-emitter voltage (open base)	V_{CEO}	max.	40	V
Emitter-base voltage (open collector)	V_{EBO}	max.	6	V
Collector current (d.c.)	I_C	max.	200	mA
Total power dissipation* up to T_{amb} = 25 °C	P_{tot}	max.	300	mW
Storage temperature	T_{stg}		−65 to +150	°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE**

$T_j = P\ (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance from junction to ambient*	$R_{th\ j\text{-}a}$	=	430	K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Collector-emitter breakdown voltage▲ I_C = 1 mA; I_B = 0	$V_{(BR)CEO}$	min.	40	V
Collector-base breakdown voltage I_C = 10 μA; I_E = 0	$V_{(BR)CBO}$	min.	60	V
Emitter-base breakdown voltage I_E = 10 μA; I_C = 0	$V_{(BR)EBO}$	min.	6	V
Collector cut-off current V_{CE} = 30 V; V_{EB} = 3 V	I_{CEX}	max.	50	nA
Output capacitance at f = 1 MHz I_E = 0; V_{CB} = 5 V	C_c	max.	4	pF
Input capacitance at f = 1 MHz I_C = 0; V_{BE} = 0,5 V	C_e	max.	8	pF
Base current with reverse biased emitter junction V_{EB} = 3 V; V_{CE} = 30 V	I_{BEX}	max.	50	nA

* Mounted on a ceramic substrate: area = 10 x 8 mm^2; thickness = 0,7 mm.

** See Thermal characteristics.

▲ Pulse test conditions: t_p = 300 μs; duty cycle ⩽ 2%.

			PMBT3903	PMBT3904	
Saturation voltages					
I_C = 10 mA; I_B = 1 mA	V_{CEsat}	max.	0,2		V
I_C = 50 mA; I_B = 5 mA	V_{CEsat}	max.	0,3		V
I_C = 10 mA; I_B = 1 mA	V_{BEsat}	min.	0,65		V
		max.	0,85		V
I_C = 50 mA; I_B = 5 mA	V_{BEsat}	max.	0,95		V
D.C. current gain *					
I_C = 0,1 mA; V_{CE} = 1 V	h_{FE}	>	20	40	
I_C = 1 mA; V_{CE} = 1 V	h_{FE}	>	35	70	
I_C = 10 mA; V_{CE} = 1 V	h_{FE}	>	50	100	
		<	150	300	
I_C = 50 mA; V_{CE} = 1 V	h_{FE}	>	30	60	
I_C = 100 mA; V_{CE} = 1 V	h_{FE}	>	15	30	
Transition frequency at f = 100 MHz					
I_C = 10 mA; V_{CE} = 20 V	f_T	min.	250	300	MHz
Noise figure at R_S = 1 kΩ					
I_C = 100 µA; V_{CE} = 5 V					
f = 10 Hz to 15,7 kHz	F	max.	6	5	dB
h-parameters (common emitter)					
I_C = 1 mA; V_{CE} = 10 V; f = 1 kHz					
Input impedance	h_{ie}		1 to 8	1 to 10	kΩ
Reverse voltage transfer ratio	h_{re}		0,1 to 5	0,5 to 8	10^{-4}
Small-signal current gain	h_{fe}		50 to 200	100 to 400	
Output admittance	h_{oe}		1 to 40	1 to 40	µS
Switching times					
Turn-on time when V_{CC} = 3 V; V_{BE} = 0,5 V					
I_C = 10 mA; I_{Bon} = 1 mA					
Delay time	t_d	<	35	35	ns
Rise time	t_r	<	35	35	ns
Turn-off time when V_{CC} = 3 V; I_C = 10 mA					
I_{Bon} = I_{Boff} = 1 mA					
Storage time	t_s	<	175	200	ns
Fall time	t_f	<	50	50	ns

* Pulse test conditions: t_p = 300 µs; duty cycle ≤ 2%.

SILICON EPITAXIAL TRANSISTOR

P-N-P transistor in a microminiature (SMD) plastic envelope intended for surface mounted applications. The PMBT3906 is primarily intended for use in telephony and professional communication equipment.

QUICK REFERENCE DATA

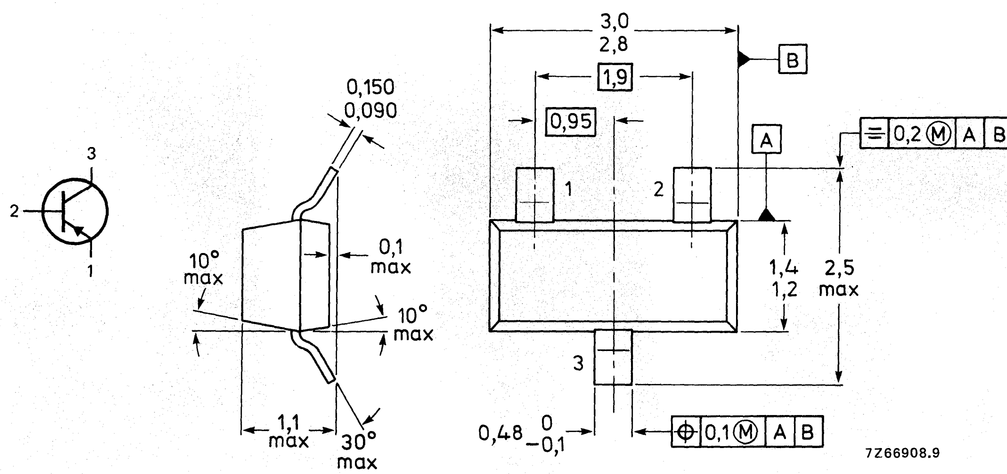
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	40	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	40	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5	V
Collector current (d.c.)	$-I_C$	max.	200	mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300	mW
D.C. current gain $-I_C$ = 10 mA; $-V_{CE}$ = 1 V	h_{FE}		100 to 300	
Transition frequency at f = 100 MHz $-I_C$ = 10 mA; $-V_{CE}$ = 20 V	f_T	min.	250	MHz

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-23.

Marking code
PMBT3906 : P2A



TOP VIEW

See also Soldering recommendations.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	40 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	40 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5 V
Collector current (d.c.)	$-I_C$	max.	200 mA
Total power dissipation* up to T_{amb} = 25 °C	P_{tot}	max.	300 mW
Storage temperature	T_{stg}		−55 to +150 °C

THERMAL CHARACTERISTICS**

$T_j = P(R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance from junction to ambient	$R_{th\ j\text{-}a}$	=	420 K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

Collector-emitter breakdown voltage▲ $-I_C$ = 1 mA; I_B = 0	$-V_{(BR)CEO}$	min.	40 V
Collector-base breakdown voltage $-I_C$ = 10 μA; I_E = 0	$-V_{(BR)CBO}$	min.	40 V
Emitter-base breakdown voltage $-I_E$ = 10 μA; I_C = 0	$-V_{(BR)EBO}$	min.	5 V
Collector cut-off current $-V_{CE}$ = 30 V; $-V_{EB}$ = 3 V	$-I_{CE}$	max.	50 nA
Base current with reverse biased emitter junction	$-I_{BEX}$	max.	50 nA
Output capacitance at f = 100 kHz I_E = 0; $-V_{CB}$ = 5 V	C_c	max.	4,5 pF
Input capacitance at f = 100 kHz I_C = 0; $-V_{BE}$ = 0,5 V	C_e	max.	10 pF

* Mounted on a ceramic substrate: area = 10 x 8 mm; thickness = 0,7 mm.
** See Thermal characteristics.
▲ Pulse test conditions: t_p = 300 μs; duty cycle ≤ 2%.

Saturation voltages				
$-I_C$ = 10 mA; $-I_B$ = 1 mA	$-V_{CEsat}$	max.	0,25	V
$-I_C$ = 50 mA; $-I_B$ = 5 mA	$-V_{CEsat}$	max.	0,4	V
		min.	0,65	V
$-I_C$ = 10 mA; $-I_B$ = 1 mA	$-V_{BEsat}$	max.	0,85	V
$-I_C$ = 50 mA; $-I_B$ = 5 mA	$-V_{BBsat}$	max.	0,95	V
D.C. current gain				
$-I_C$ = 0,1 mA; $-V_{CE}$ = 1 V	h_{FE}	min.	60	
$-I_C$ = 1 mA; $-V_{CE}$ = 1 V	h_{FE}	min.	80	
$-I_C$ = 10 mA; $-V_{CE}$ = 1 V	h_{FE}	min.	100	
		max.	300	
$-I_C$ = 50 mA; $-V_{CE}$ = 1 V	h_{FE}	min.	60	
$-I_C$ = 100 mA; $-V_{CE}$ = 1 V	h_{FE}	min.	30	
Transition frequency at f = 100 MHz				
$-I_C$ = 10 mA; $-V_{CE}$ = 20 V	f_T	min.	250	MHz
Noise figure at R_S = 1 kΩ				
$-I_C$ = 100 μA; $-V_{CE}$ = 5 V				
f = 10 Hz to 15,7 kHz	F	max.	4	dB
h-parameters (common emitter)				
$-I_C$ = 1 mA; $-V_{CE}$ = 10 V; f = 1 kHz				
Input impedance	h_{ie}	min.	2,0	kΩ
		max.	12	kΩ
Reverse voltage transfer ratio	h_{re}	min.	1,0	10^{-4}
		max.	10	10^{-4}
Small signal current gain	h_{fe}	min.	100	
		max.	400	
Output admittance	h_{oe}	min.	30	μS
		max.	60	μS
Switching times				
Turn-on time when $-V_{CC}$ = 3 V; $-V_{BE}$ = 0,5 V				
$-I_C$ = 10 mA; $-I_{Bon}$ = 1 mA				
Delay time	t_d	max.	35	ns
Rise time	t_r	max.	35	ns
Turn-off time when $-V_{CC}$ = 3 V; $-I_C$ = 10 mA				
$-I_{Bon}$ = $-I_{Boff}$ = 1 mA				
Storage time	t_s	max.	225	ns
Fall time	t_f	max.	75	ns

SILICON EPITAXIAL TRANSISTORS

N-P-N transistors in a microminiature (SMD) plastic envelope intended for application in thick and thin film circuits (Surface Mounted Device).

They are primarily intended for use in telephony and professional communication equipment.

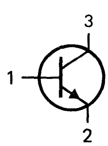
QUICK REFERENCE DATA

			PMBT6428	PMBT6429	
Collector-base voltage (open emitter)	V_{CBO}	max.	60	55	V
Collector-emitter voltage (open base)	V_{CEO}	max.	50	45	V
Collector current (d.c.)	I_C	max.	200		mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	350		mW
D.C. current gain I_C = 0,1 mA; V_{CE} = 5 V	h_{FE}	min. max.	250 650	500 1250	
I_C = 1 mA; V_{CE} = 5 V	h_{FE}	min.	250	500	
Transition frequency at f = 100 MHz I_C = 1 mA; V_{CE} = 5 V	f_T	min. max.	100 700		MHz MHz
Input capacitance at f = 1 MHz I_C = 0; V_{EB} = 0,5 V	C_e	max.	8,0		pF

MECHANICAL DATA

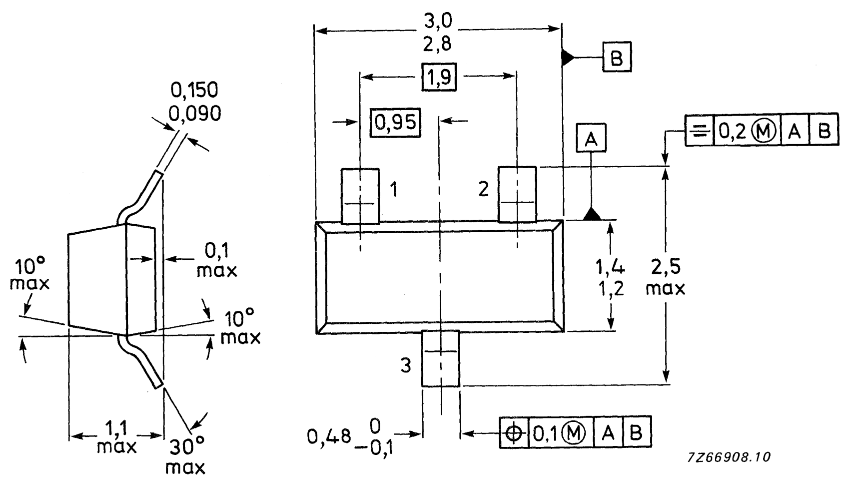
Dimensions in mm

Fig. 1 SOT-23.



Marking code

PMBT6428: P1K
PMBT6429: P1L



TOP VIEW

See also Soldering recommendations.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			PMBT6428	PMBT6429	
Collector-base voltage (open emitter)	V_{CBO}	max.	60	55	V
Collector-emitter voltage (open base)	V_{CEO}	max.	50	45	V
Emitter-base voltage (open collector)	V_{EBO}	max.	6,0		V
Collector current (d.c.)	I_C	max.	200		mA
Total power dissipation* up to T_{amb} = 25 °C	P_{tot}		350		mW
Storage temperature	T_{stg}		−55 to +150		°C
Junction temperature	T_j	max.	150		°C

THERMAL CHARACTERISTICS

Thermal resistance from junction to ambient*	$R_{th\ j\text{-}a}$	=	350	K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

			PMBT6428	PMBT6429	
Collector-emitter breakdown voltage I_C = 1 mA; I_B = 0	$V_{(BR)CEO}$	min.	50	45	V
Collector-base breakdown voltage I_C = 0,1 mA; I_E = 0	$V_{(BR)CBO}$	min.	60	55	V
Collector cut-off current V_{CE} = 30 V	I_{CEO}	max.	100		nA
I_E = 0; V_{CB} = 30 V	I_{CBO}	max.	10		nA
Emitter cut-off current I_C = 0; V_{EB} = 5 V	I_{EBO}	max.	10		nA
Base-emitter On-voltage I_C = 1 mA; V_{CE} = 5 V	$V_{BE(on)}$	min.	560		mV
		max.	660		mV

* Mounted on a ceramic substrate of 15 mm x 15 mm x 0,7 mm.

			PMBT6428	PMBT6429	
Collector-emitter saturation voltage					
I_C = 10 mA; I_B = 0,5 mA	V_{CEsat}	max.	0,2		V
I_C = 100 mA; I_B = 5 mA	V_{CEsat}	max.	0,6		V
D.C. current gain					
I_C = 0,1 mA; V_{CE} = 5 V	h_{FE}	min.	250	500	
I_C = 0,1 mA; V_{CE} = 5 V	h_{FE}	min. max.	250 650	500 1250	
I_C = 1 mA; V_{CE} = 5 V	h_{FE}	min.	250	500	
I_C = 10 mA; V_{CE} = 5 V	h_{FE}	min.	250	500	
Transition frequency at f = 100 MHz					
I_C = 1 mA; V_{CE} = 5 V	f_T	min. max.	100 700		MHz MHz
Output capacitance at f = 1 MHz					
I_E = 0; V_{CB} = 10 V	C_c	max.	3,0		pF
Input capacitance at f = 1 MHz					
I_C = 0; V_{EB} = 0,5 V	C_e	max.	8,0		pF

SILICON EPITAXIAL TRANSISTORS

N-P-N transistors in a microminiature (SMD) plastic envelope intended for surface mounted applications. They are primarily intended for use in telephony and professional communication equipment.

QUICK REFERENCE DATA

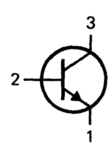
			PMBTA05	PMBTA06	
Collector-base voltage (open emitter)	V_{CBO}	max.	60	80	V
Collector-emitter voltage (open base)	V_{CEO}	max.	60	80	V
Emitter-base voltage (open collector)	V_{EBO}	max.	4		V
Collector current (d.c.)	I_C	max.	500		mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300		mW
D.C. current gain I_C = 100 mA; V_{CE} = 1 V	h_{FE}	min.	50		
Transition frequency at f = 100 MHz I_C = 10 mA; V_{CE} = 2 V	f_T	min.	100		MHz
Collector-emitter saturation voltage I_C = 100; I_B = 10 mA	V_{CEsat}	max.	0,25		V

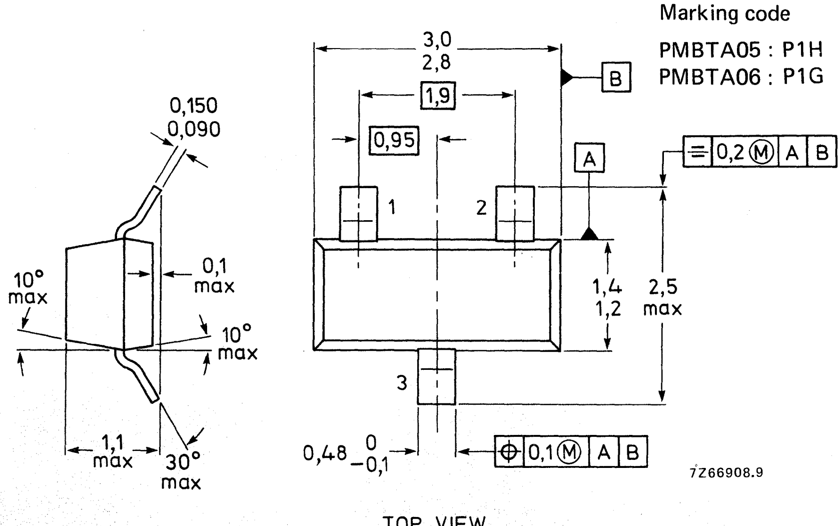
MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-23.

Marking code
PMBTA05 : P1H
PMBTA06 : P1G





See also Soldering recommendations.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			PMBTA05	PMBTA06	
Collector-base voltage	V_{CBO}	max.	60	80	V
Collector-emitter voltage (open base)	V_{CEO}	max.	60	80	V
Emitter-base voltage (open collector)	V_{EBO}	max.	4		V
Collector current (d.c.)	I_C	max.	500		mA
Total power dissipation * up to T_{amb} = 25 °C	P_{tot}	max.	300		mW
Storage temperature	T_{stg}		−65 to +150		°C
Junction temperature	T_j	max.	150		°C

THERMAL CHARACTERISTICS **

$T_j = P (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance from junction to ambient	$R_{th\ j\text{-}a}$	=	430	K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

			PMBTA05	PMBTA06	
Collector-emitter breakdown voltage ▲ I_C = 1 mA; I_B = 0	$V_{(BR)CEO}$	min.	60	80	V
Emitter-base breakdown voltage I_C = 0; I_E = 100 μA	$V_{(BR)EBO}$	min.	4		V
Collector cut-off current V_{CE} = 60 V; I_B = 0	I_{CEO}	max.	0,1		μA
Collector cut-off current V_{CB} = 60 V; I_E = 0	I_{CBO}	max.	0,1		μA
V_{CB} = 80 V; I_E = 0	I_{CBO}	max.	0,1		μA
Saturation voltages I_C = 100 mA; I_B = 10 mA	V_{CEsat}	max.	0,25		V
Base-emitter on voltage I_C = 100 mA; V_{CE} = 1 V	$V_{BE(on)}$	max.	1,2		V
D.C. current gain I_C = 10 mA; V_{CE} = 1 V	h_{FE}	min.	50		
I_C = 100 mA; V_{CE} = 1 V	h_{FE}	min.	50		
Transition frequency at f = 100 MHz I_C = 10 mA; V_{CE} = 2 V	f_T	min.	100		MHz

* Mounted on a ceramic substrate: area = 10 x 8 mm; thickness = 0,7 mm.
** See Thermal characteristics.
▲ Pulse test conditions: t_p = 300 μs; duty cycle ≤ 2%.

N-P-N SMALL-SIGNAL DARLINGTON TRANSISTORS

N-P-N small-signal darlington transistors in a microminiature SMD envelope (SOT-23).
Designed primarily for preamplifier input applications requiring high input impedance.
P-N-P complement is the PMBTA63/64.

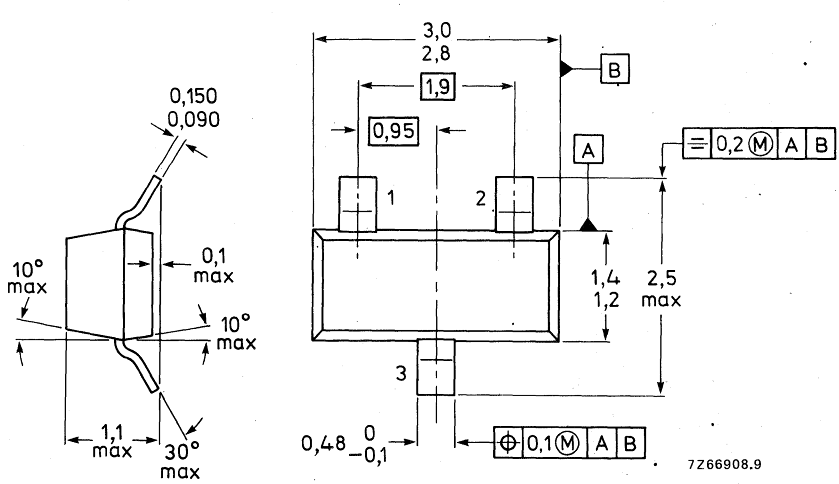
QUICK REFERENCE DATA

Collector-emitter voltage $V_{BE} = 0$		V_{CES}	max.	30	V
Collector current (d.c.)		I_C	max.	300	mA
Total power dissipation up to $T_{amb} = 25\ ^oC$		P_{tot}	max.	300	mW
Junction temperature		T_j	max.	150	^oC
D.C. current gain $I_C = 10$ mA; $V_{CE} = 5$ V	PMBTA13	h_{FE}	min.	5000	
	PMBTA14	h_{FE}	min.	10 000	
Transition frequency at f = 100 MHz $I_C = 10$ mA; $V_{CE} = 5$ V		f_T	min.	125	MHz

MECHANICAL DATA

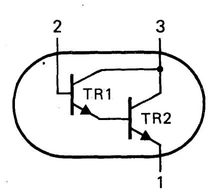
Dimensions in mm

Fig. 1 SOT-23.



TOP VIEW

Marking code
PMBTA13: P1M
PMBTA14: P1N



See also Soldering recommendations.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	V_{CBO}	max.	30	V
Collector-emitter voltage $V_{BE} = 0$	V_{CES}	max.	30	V
Emitter-base voltage (open collector)	V_{EBO}	max.	10	V
Collector current (d.c.)	I_C	max.	300	mA
Total power dissipation up to $T_{amb} = 25\ ^oC$*	P_{tot}	max.	300	mW
Storage temperature	T_{stg}		−65 to +150	^oC
Junction temperature	T_j	max.	150	^oC

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j\text{-}a}$	430	K/W

CHARACTERISTICS

$T_j = 25\ ^oC$ unless otherwise specified

Collector-emitter breakdown voltage $I_C = 100\ \mu A$		$V_{(BR)CES}$	min.	30	V
Emitter-base cut-off current $V_{BE} = 10$ V		I_{EBO}	max.	0,1	μA
Collector-base cut-off current $V_{CB} = 30$ V		I_{CBO}	max.	0,1	μA
D.C. current gain $I_C = 10$ mA; $V_{CE} = 5$ V	PMBTA13	h_{FE}	min.	5000	
	PMBTA14	h_{FE}	min.	10 000	
$I_C = 100$ mA; $V_{CE} = 5$ V	PMBTA13	h_{FE}	min.	10 000	
	PMBTA14	h_{FE}	min.	20 000	
Collector-emitter saturation voltage $I_C = 100$ mA; $I_B = 0,1$ mA		V_{CEsat}	max.	1,5	V
Base-emitter ON-voltage $I_C = 100$ mA; $V_{CE} = 5$ V		$V_{BE(on)}$	max.	2,0	V
Transition frequency at f = 100 MHz $I_C = 10$ mA; $V_{CE} = 5$ V		f_T	min.	125	MHz

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

SILICON EPITAXIAL TRANSISTORS

N-P-N transistors in a microminiature (SMD) plastic envelope intended for surface mounted applications. They are primarily intended for use in telephony and professional communication equipment.

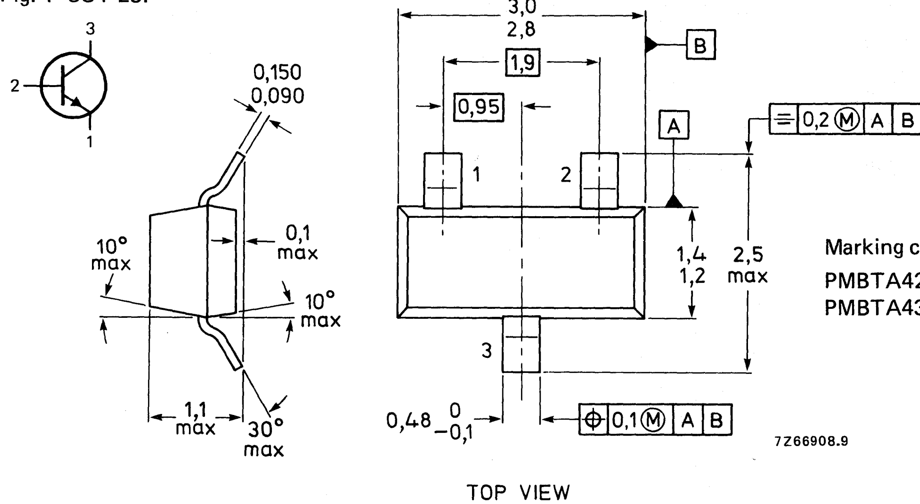
QUICK REFERENCE DATA

			PMBTA42	PMBTA43	
Collector-base voltage (open emitter)	V_{CBO}	max.	300	200	V
Collector-emitter voltage (open base)	V_{CEO}	max.	300	200	V
Emitter-base voltage (open collector)	V_{EBO}	max.	6	6	V
Collector current (d.c.)	I_C	max.	500	500	mA
Total power dissipation up to T_{amb} = 35 °C	P_{tot}	max.	310	310	mW
Junction temperature	T_j	max.	150	150	°C
D.C. current gain I_C = 10 mA; V_{CE} = 10 V	h_{FE}	>	40	40	
Transition frequency at f = 35 MHz I_C = 10 mA; V_{CE} = 20 V	f_T	>	50	50	MHz
Feedback capacitance at f = 1 MHz I_C = 0; V_{CE} = 20 V	C_{re}	<	3	4	pF

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-23.



TOP VIEW

Marking code
PMBTA42 = P1D
PMBTA43 = P1E

See also Soldering recommendations.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			PMBTA42	PMBTA43	
Collector-base voltage (open emitter)	V_{CBO}	max.	300	200	V
Collector-emitter voltage (open base)	V_{CEO}	max.	300	200	V
Emitter-base voltage (open collector)	V_{EBO}	max.	6		V
Collector current (d.c.)	I_C	max.	500		mA
Total power dissipation (note 1) up to T_{amb} = 35 °C	P_{tot}	max.	310		mW
Storage temperature	T_{stg}		−65 to +150		°C
Junction temperature	T_j	max.	150		°C

THERMAL CHARACTERISTICS (note 2)

$T_j = P (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance from junction to ambient	$R_{th\ j\text{-}a}$	=	430	K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

			PMBTA42	PMBTA43	
Collector-emitter breakdown voltage (note 3) I_C = 1 mA; I_B = 0	$V_{(BR)CEO}$	>	300	200	V
Collector-base breakdown voltage I_C = 100 μA; I_E = 0	$V_{(BR)CBO}$	>	300	200	V
Emitter-base breakdown voltage I_E = 100 μA; I_C = 0	$V_{(BR)EBO}$	>	6	6	V
Collector cut-off current I_E = 0; V_{CB} = 200 V	I_{CBO}	<	0,1	–	μA
I_E = 0; V_{CB} = 160 V	I_{CBO}	<	–	0,1	μA
Emitter cut-off current I_C = 0; V_{BE} = 6 V	I_{EBO}	<	0,1	–	μA
I_C = 0; V_{BE} = 4 V	I_{EBO}	<	–	0,1	μA
Feedback capacitance at f = 1 MHz I_E = 0; V_{CB} = 20 V	C_{re}	<	3	4	pF

Notes

1. Mounted on a ceramic substrate: area = 2,5 cm^2; thickness 0,7 mm.
2. See Thermal characteristics.
3. Pulse test conditions: t_p = 300 μs; δ = 0,02.

Saturation voltages				
I_C = 20 mA; I_B = 2 mA	V_{CEsat}	<	0,5	V
	V_{BEsat}	<	0,9	V
D.C. current gain				
I_C = 1 mA; V_{CE} = 10 V		>	25	
I_C = 10 mA; V_{CE} = 10 V	h_{FE}	>	40	
I_C = 30 mA; V_{CE} = 10 V		>	40	
Transition frequency at f = 100 MHz				
I_C = 10 mA; V_{CE} = 20 V	f_T	>	50	MHz

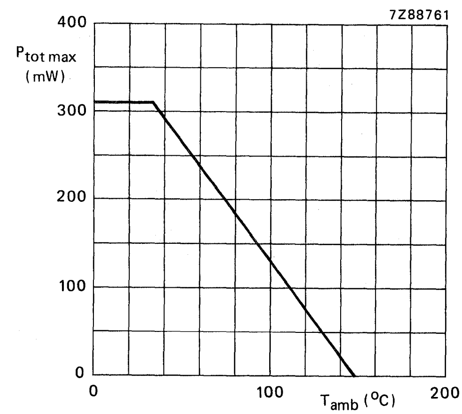


Fig. 2 Power derating curve.

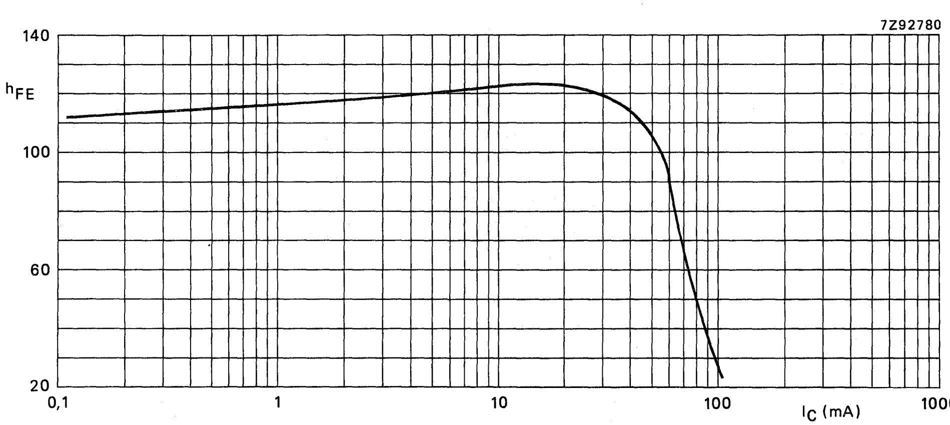


Fig. 3 T_j = 25 °C; V_{CE} = 20 V; typical values.

SILICON EPITAXIAL TRANSISTORS

P-N-P transistors in a microminiature (SMD) plastic envelope intended for surface mounted applications. They are primarily intended for use in telephony and professional communication equipment.

QUICK REFERENCE DATA

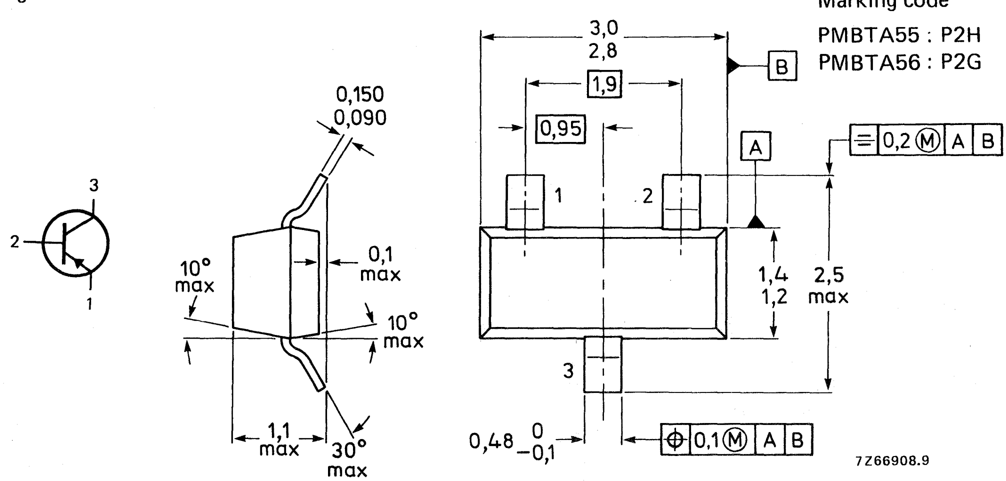
			PMBTA55	PMBTA56	
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	60	80	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	60	80	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	4		V
Collector current (d.c.)	$-I_C$	max.	500		mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300		mW
D.C. current gain $-I_C$ = 100 mA; $-V_{CE}$ = 1 V	h_{FE}	min.	50		
Transition frequency at f = 100 MHz $-I_C$ = 100 mA; $-V_{CE}$ = 1 V	f_T	min.	50		MHz
Collector-emitter saturation voltage $-I_C$ = 100; I_B = 10 mA	V_{CEsat}	max.	0,25		V

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOT-23.

Marking code
PMBTA55 : P2H
PMBTA56 : P2G



TOP VIEW

See also Soldering recommendations.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			PMBTA55	PMBTA56	
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	60	80	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	60	80	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	4		V
Collector current (d.c.)	$-I_C$	max.	500		mA
Total power dissipation * up to T_{amb} = 25 °C	P_{tot}	max.	300		mW
Storage temperature	T_{stg}		−65 to +150		°C
Junction temperature	T_j	max.	150		°C

THERMAL CHARACTERISTICS**

$T_j = P\,(R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance from junction to ambient	$R_{th\ j\text{-}a}$	=	430	K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

			PMBTA55	PMBTA56	
Collector-emitter breakdown voltage▲ $-I_C$ = 1 mA; I_B = 0	$-V_{(BR)CEO}$	min.	60	80	V
Emitter-base breakdown voltage $-I_C$ = 0; I_E = 100 μA	$-V_{(BR)EBO}$	min.	4		V
Collector cut-off current $-V_{CE}$ = 60 V; I_B = 0	$-I_{CEO}$	max.	0,1		μA
Collector cut-off current $-V_{CB}$ = 60 V; I_E = 0	$-I_{CBO}$	max.	0,1		μA
$-V_{CB}$ = 80 V; I_E = 0	$-I_{CBO}$	max.	0,1		μA
Saturation voltages $-I_C$ = 100 mA; $-I_B$ = 10 mA	$-V_{CEsat}$	max.	0,25		V
Base-emitter on voltage $-I_C$ = 100 mA; $-V_{CE}$ = 1 V	$-V_{BE(on)}$	max.	1,2		V
D.C. current gain $-I_C$ = 10 mA; $-V_{CE}$ = 1 V	h_{FE}	min.	50		
$-I_C$ = 100 mA; $-V_{CE}$ = 1 V	h_{FE}	min.	50		
Transition frequency at f = 100 MHz $-I_C$ = 100 mA; $-V_{CE}$ = 1 V	f_T	min.	50		MHz

* Mounted on a ceramic substrate: area = 10 x 8 mm; thickness = 0,7 mm.
** See Thermal characteristics.
▲ Pulse test conditions: t_p = 300 μs; duty cycle ≤ 2%.

P-N-P SMALL-SIGNAL DARLINGTON TRANSISTORS

P-N-P small-signal darlington transistors in a microminiature SMD envelope (SOT-23).
Designed primarily for preamplifier input applications requiring high input impedance.
N-P-N complement is the PMBTA13/14.

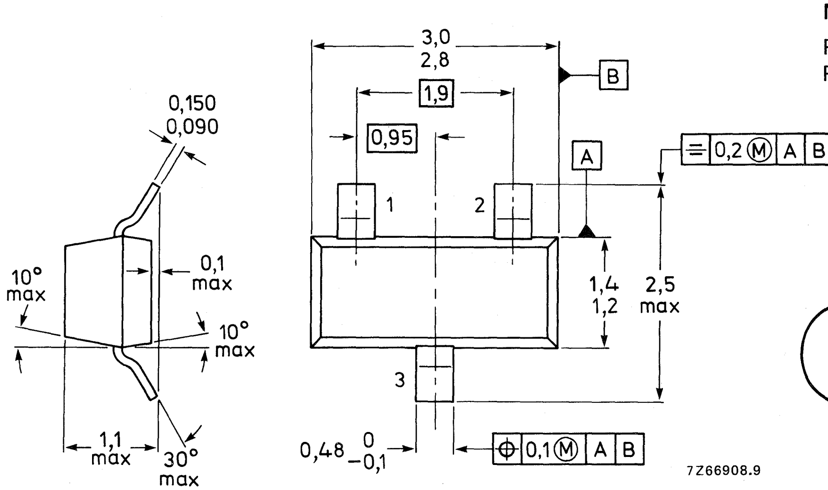
QUICK REFERENCE DATA

Collector-emitter voltage $V_{BE} = 0$		$-V_{CES}$	max.	30	V
Collector current (d.c.)		$-I_C$	max.	500	mA
Total power dissipation up to $T_{amb} = 25\ ^oC$		P_{tot}	max.	300	mW
Junction temperature		T_j	max.	150	^oC
D.C. current gain $-I_C = 10$ mA; $-V_{CE} = 5$ V	PMBTA63	h_{FE}	min.	5000	
	PMBTA64	h_{FE}	min.	10 000	
Transition frequency at f = 100 MHz $-I_C = 10$ mA; $-V_{CE} = 50$ V		f_T	min.	125	MHz

MECHANICAL DATA

Dimensions in mm

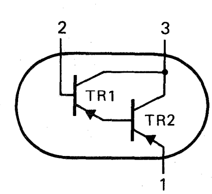
Fig. 1 SOT-23.



TOP VIEW

Marking code

PMBTA63: P2U
PMBTA64: P2V



See also Soldering recommendations.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	30	V
Collector-emitter voltage $V_{BE} = 0$	$-V_{CES}$	max.	30	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	10	V
Collector current (d.c.)	$-I_C$	max.	500	mA
Total power dissipation up to $T_{amb} = 25\ ^oC$*	P_{tot}	max.	500	mW
Storage temperature	T_{stg}		−65 to +150	^oC
Junction temperature	T_j	max.	150	^oC

THERMAL RESISTANCE

From junction to ambient*	$R_{th\ j\text{-}a}$		430	K/W

CHARACTERISTICS

$T_j = 25\ ^oC$ unless otherwise specified

Collector-emitter breakdown voltage $-I_C = 100\ \mu A$		$-V_{(BR)CES}$	min.	30	V
Emitter-base cut-off current $-V_{BE} = 10$ V		$-I_{EBO}$	max.	0,1	μA
Collector-base cut-off current $-V_{CB} = 30$ V		$-I_{CBO}$	max.	0,1	μA
D.C. current gain $-I_C = 10$ mA; $-V_{CE} = 5$ V	PMBTA63	h_{FE}	min.	5000	
	PMBTA64	h_{FE}	min.	10 000	
$-I_C = 100$ mA; $-V_{CE} = 5$ V	PMBTA63	h_{FE}	min.	10 000	
	PMBTA64	h_{FE}	min.	20 000	
Collector-emitter saturation voltage $-I_C = 100$ mA; $-I_B = 0,1$ mA		$-V_{CEsat}$	max.	1,5	V
Base-emitter ON-voltage $-I_C = 100$ mA; $-V_{CE} = 5$ V		$-V_{BE(on)}$	max.	2,0	V
Transition frequency at f = 100 MHz $-I_C = 10$ mA; $-V_{CE} = 50$ V; $T_{amb} = 25\ ^oC$		f_T	min.	125	MHz

* Mounted on a ceramic substrate of 8 mm x 10 mm x 0,7 mm.

SILICON EPITAXIAL TRANSISTORS

P-N-P transistors in a microminiature (SMD) plastic envelope intended for surface mounted applications. They are primarily intended for use in telephony and professional communication equipment.

QUICK REFERENCE DATA

			PMBTA92	PMBTA93	
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	300	200	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	300	200	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5		V
Collector current (d.c.)	$-I_C$	max.	500		mA
Total power dissipation up to T_{amb} = 25 °C	P_{tot}	max.	300		mW
D.C. current gain $-I_C$ = 10 mA; $-V_{CE}$ = 10 V	h_{FE}	min.	40		
Transition frequency at f = 100 MHz $-I_C$ = 10 mA; $-V_{CE}$ = 20 V	f_T	min.	50		MHz
Collector-base capacitance at f = 1 MHz I_E = 0; $-V_{CB}$ = 20 V	C_{cb}	max.	6	8	pF

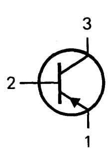
MECHANICAL DATA

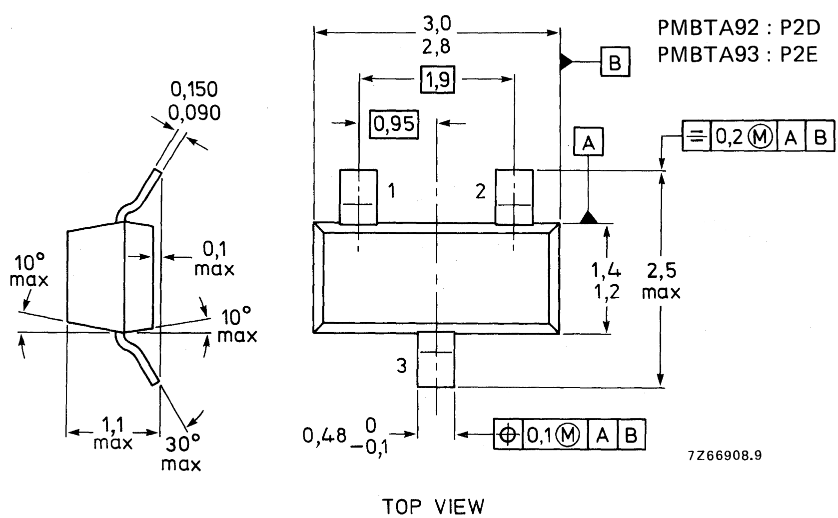
Dimensions in mm

Fig. 1 SOT-23.

Marking code

PMBTA92 : P2D
PMBTA93 : P2E





See also Soldering recommendations.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

			PMBTA92	PMBTA93	
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	300	200	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	300	200	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5		V
Collector current (d.c.)	$-I_C$	max.	500		mA
Total power dissipation * up to T_{amb} = 25 °C	P_{tot}	max.	300		mW
Storage temperature	T_{stg}		−65 to +150		°C
Junction temperature	T_j	max.	150		°C

THERMAL CHARACTERISTICS **

$T_j = P\ (R_{th\ j\text{-}t} + R_{th\ t\text{-}s} + R_{th\ s\text{-}a}) + T_{amb}$

Thermal resistance from junction to ambient*	$R_{th\ j\text{-}a}$	=	430	K/W

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified

			PMBTA92	PMBTA93	
Collector-emitter breakdown voltage $-I_C$ = 1 mA; I_B = 0	$-V_{(BR)CEO}$	min.	300	200	V
Collector-base breakdown voltage $-I_C$ = 100 μA; I_E = 0	$-V_{(BR)CBO}$	min.	300	200	V
Collector cut-off current $-V_{CB}$ = 200 V; I_E = 0	$-I_{CBO}$	max.	0,25	−	μA
$-V_{CB}$ = 160 V; I_E = 0	$-I_{CBO}$	max.	−	0,25	μA
Emitter-base breakdown voltage $-I_E$ = 100 μA; I_C = 0	$-V_{(BR)EBO}$	min.	5		V
Emitter cut-off current I_C = 0; $-V_{BE}$ = 3 V	$-I_{EBO}$	max.	0,1		μA
Collector-base capacitance at f = 1 MHz; I_E = 0; $-V_{CB}$ = 20 V	C_{cb}	max.	6	8	pF
Saturation voltages $-I_C$ = 20 mA; $-I_B$ = 2 mA	$-V_{CEsat}$	max.	0,5		V
$-I_C$ = 20 mA; $-I_B$ = 2 mA	$-V_{BEsat}$	max.	0,9		V
D.C. current gain ▲ $-I_C$ = 1 mA; $-V_{CE}$ = 10 V	h_{FE}	min.	25		
$-I_C$ = 10 mA; $-V_{CE}$ = 10 V	h_{FE}	min.	40		
$-I_C$ = 30 mA; $-V_{CE}$ = 10 V	h_{FE}	min.	25		

* Mounted on a ceramic substrate: area = 10 x 8 mm; thickness = 0,7 mm.
** See Thermal characteristics.
▲ Pulse test conditions: t_p = 300 μs; duty cycle ≤ 2%.

VOLTAGE REGULATOR DIODES FOR SURFACE MOUNTING

Silicon planar diodes in a SOD-80 envelope intended for use as low-power voltage stabilizers or voltage references.
The series consists of 43 types with nominal working voltages ranging from 3,0 V to 75 V.
The SM diode is a leadless diode in a hermetically sealed glass SOD-80 envelope with tin-plated metal discs at each end. It is suitable for "automatic placement" and as such can withstand immersion soldering.

The diodes are delivered on "super 8" tape.

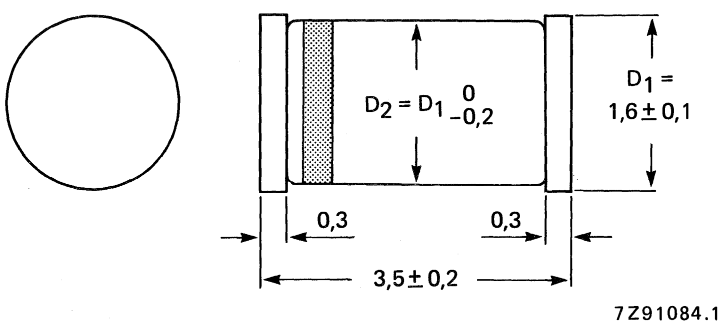
QUICK REFERENCE DATA

Working voltage range	V_Z	nom.	3,0 to 75	V
Working voltage tolerance			± 5	%
Total power dissipation	P_{tot}	max.	500	mW
Non-repetitive peak reverse power dissipation T_j = 55 °C; t_p = 8,3 ms, square wave	P_{ZSM}	max.	10	W
Junction temperature	T_j		−65 to + 200	°C

MECHANICAL DATA

Dimensions in mm

Fig. 1 SOD-80.



Cathode indicated by yellow band.

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Average forward current (averaged over any 20 ms period)	$I_{F(AV)}$	max.	250 mA
Repetitive peak forward current	I_{FRM}	max.	250 mA
Total power dissipation if flanges are kept at T_{flange} = 75 °C	P_{tot}	max.	500 mW
Derating factor			4 mW/K
Non-repetitive peak reverse power dissipation T_j = 55 °C; t_p = 8,3 ms, square wave	P_{ZSM}	max.	10 W
Storage temperature	T_{stg}	−65 to + 200 °C	
Junction temperature	T_j	−65 to + 200 °C	

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise stated

Forward voltage I_F = 200 mA	V_F	max.	1,1 V

type number	working voltage V_Z (V) at I_{ztest} (note 1) nom.	test current I_{Ztest} (mA)	max. Zener impedance Z_{ZT} (Ω) at I_{Ztest} (note 2)	differential resistance r_{diff} (Ω) at I_{ZK} = 0,25 mA (note 2) max.	reverse current I_R (μA) at V_R max.	test voltage V_R (V)	temp. coeff. S_Z (%/K) (note 3) max.
PMLL5225B	3,0	20	29	1600	50	1,0	−0,075
PMLL5226B	3,3	20	28	1600	25	1,0	−0,070
PMLL5227B	3,6	20	24	1700	15	1,0	−0,065
PMLL5228B	3,9	20	23	1900	10	1,0	−0,060
PMLL5229B	4,3	20	22	2000	5	1,0	± 0,055
PMLL5230B	4,7	20	19	1900	5	2,0	± 0,030
PMLL5231B	5,1	20	17	1600	5	2,0	± 0,030
PMLL5232B	5,6	20	11	1600	5	3,0	+ 0,038
PMLL5233B	6,0	20	7	1600	5	3,5	+ 0,038
PMLL5234B	6,2	20	7	1000	5	4,0	+ 0,045
PMLL5235B	6,8	20	5	750	3	5,0	+ 0,050
PMLL5236B	7,5	20	6	500	3	6,0	+ 0,058
PMLL5237B	8,2	20	8	500	3	6,5	+ 0,062
PMLL5238B	8,7	20	8	600	3	6,5	+ 0,065
PMLL5239B	9,1	20	10	600	3	7,0	+ 0,068

type number	working voltage V_Z (V) at I_{ztest} (note 1) nom.	test current I_{Ztest} (mA)	max. Zener impedance Z_{ZT} (Ω) at I_{Ztest} (note 2)	differential resistance r_{diff} (Ω) at I_{ZK} = 0,25 mA (note 2) max.	reverse current I_R (μA) at V_R max.	test voltage V_R (V)	temp. coeff. S_Z (%/K) (note 3) max.
PMLL5240B	10	20	17	600	3	8,0	+ 0,075
PMLL5241B	11	20	22	600	2	8,4	+ 0,076
PMLL5242B	12	20	30	600	1	9,1	+ 0,077
PMLL5243B	13	9,5	13	600	0,5	9,9	+ 0,079
PMLL5244B	14	9,0	15	600	0,1	10	+ 0,082
PMLL5245B	15	8,5	16	600	0,1	11	+ 0,082
PMLL5246B	16	7,8	17	600	0,1	12	+ 0,083
PMLL5247B	17	7,4	19	600	0,1	13	+ 0,084
PMLL5248B	18	7,0	21	600	0,1	14	+ 0,085
PMLL5249B	19	6,6	23	600	0,1	14	+ 0,086
PMLL5250B	20	6,2	25	600	0,1	15	+ 0,086
PMLL5251B	22	5,6	29	600	0,1	17	+ 0,087
PMLL5252B	24	5,2	33	600	0,1	18	+ 0,088
PMLL5253B	25	5,0	35	600	0,1	19	+ 0,089
PMLL5254B	27	4,6	41	600	0,1	21	+ 0,090
PMLL5255B	28	4,5	44	600	0,1	21	+ 0,091
PMLL5256B	30	4,2	49	600	0,1	23	+ 0,091
PMLL5257B	33	3,8	58	700	0,1	25	+ 0,092
PMLL5258B	36	3,4	70	700	0,1	27	+ 0,093
PMLL5259B	39	3,2	80	800	0,1	30	+ 0,094
PMLL5260B	43	3,0	93	900	0,1	33	+ 0,095
PMLL5261B	47	2,7	105	1000	0,1	36	+ 0,095
PMLL5262B	51	2,5	125	1100	0,1	39	+ 0,096
PMLL5263B	56	2,2	150	1300	0,1	43	+ 0,096
PMLL5264B	60	2,1	170	1400	0,1	46	+ 0,097
PMLL5265B	62	2,0	185	1400	0,1	47	+ 0,097
PMLL5266B	68	1,8	230	1600	0,1	52	+ 0,097
PMLL5267B	75	1,7	270	1700	0,1	56	+ 0,098

Notes

1. V_Z is measured with device at thermal equilibrium while held in clips in still air at 25 °C.
2. $I_{(ac\,rms)}$ = 10% of I_{Ztest} resp. I_{ZK}, 60 Hz superimposed.
3. For types PMLL5225B to PMLL5242B the current I_Z = 7,5 mA; for PMLL5243B and higher $I_Z = I_{Ztest}$. Testpoints at T_1 = 25 °C, T_2 = 125 °C.

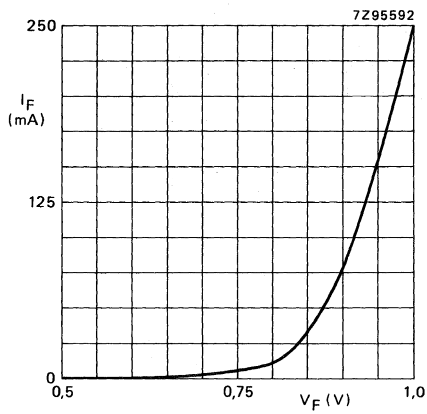


Fig. 2 T_{amb} = 25 °C; typical values.

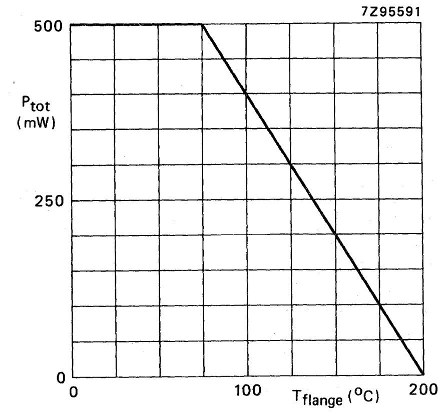


Fig. 3 Total power dissipation versus flange temperature.

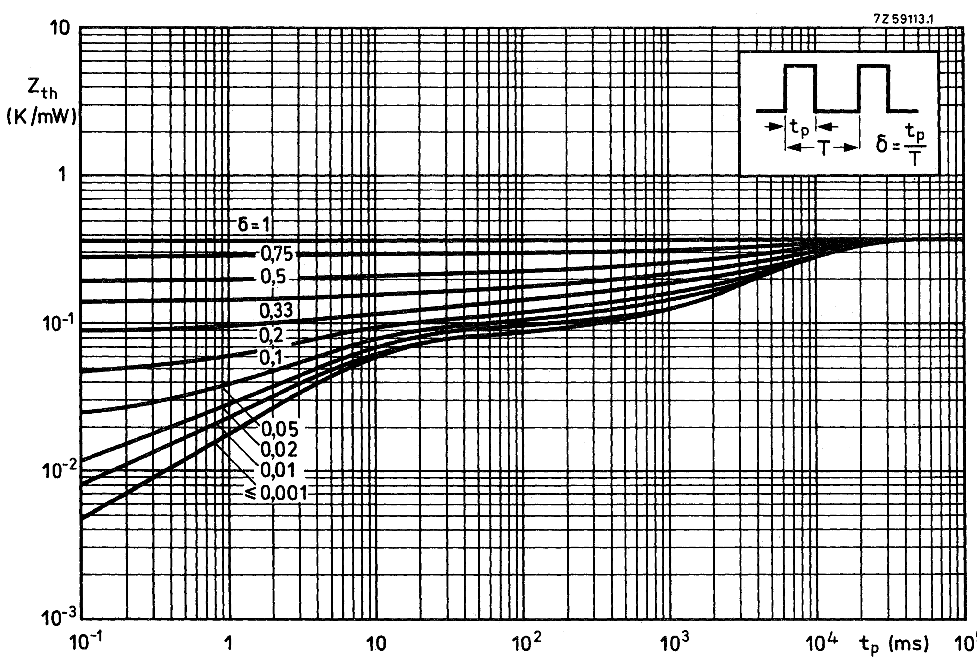


Fig. 4 Thermal impedance versus pulse duration.

SILICON PLANAR EPITAXIAL TRANSISTOR

N-P-N transistor in a SOT-89 envelope primarily intended for high-speed, saturated switching applications for industrial service.

QUICK REFERENCE DATA

Collector-base voltage (open emitter)	V_{CBO}	max.	60 V
Collector-emitter voltage (open base)	V_{CEO}	max.	40 V
Collector current (d.c.)	I_C	max.	200 mA
Total power dissipation at T_{amb} = 25 °C	P_{tot}	max.	1,0 W
Junction temperature	T_j	max.	150 °C
D.C. current gain I_C = 10 mA; V_{CE} = 1 V	h_{FE}	> <	100 300
Transistion frequency at f = 100 MHz I_C = 10 mA; V_{CE} = 20 V	f_T	>	300 MHz
Storage time I_{Con} = 10 mA; I_{Bon} = $-I_{Boff}$ = 1 mA	t_s	<	200 ns

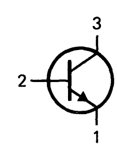
MECHANICAL DATA

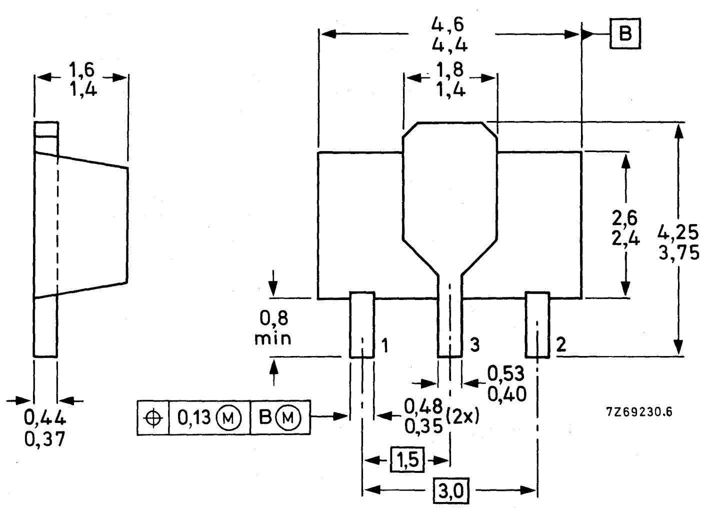
Dimensions in mm

Fig. 1 SOT-89.

Marking code

P1A





BOTTOM VIEW

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	V_{CBO}	max.	60 V
Collector-emitter voltage (open base)	V_{CEO}	max.	40 V
Emitter-base voltage (open collector)	V_{EBO}	max.	6 V
Collector current (d.c.)	I_C	max.	200 mA
Total power dissipation at T_{amb} = 25 °C*	P_{tot}	max.	1,0 W
Storage temperature	T_{stg}		−55 to +150 °C
Junction temperature	T_j	max.	150 °C

THERMAL RESISTANCE

From junction to ambient in free air	$R_{th\ j\text{-}a}$	=	125 K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Currents at reverse biased emitter junction			
V_{CE} = 30 V; $-V_{BE}$ = 3 V	I_{CEX}	<	50 nA
	$-I_{BEX}$	<	50 nA
Saturation voltages			
I_C = 10 mA; I_B = 1 mA	V_{CEsat}	<	200 mV
	V_{BEsat}		650 to 850 mV
I_C = 50 mA; I_B = 5 mA	V_{CEsat}	<	300 mV
	V_{BEsat}	<	950 mV
D.C. current gain			
I_C = 0,1 mA; V_{CE} = 1 V	h_{FE}	>	40
I_C = 1 mA; V_{CE} = 1 V	h_{FE}	>	70
I_C = 10 mA; V_{CE} = 1 V	h_{FE}	>	100
		<	300
I_C = 50 mA; V_{CE} = 1 V	h_{FE}	>	60
I_C = 100 mA; V_{CE} = 1 V	h_{FE}	>	30
Collector capacitance at 100 kHz $\leqslant f \leqslant$ 1 MHz			
$I_E = I_e = 0$; V_{CB} = 5 V	C_c	<	4,0 pF
Emitter capacitance at 100 kHz $\leqslant f \leqslant$ 1 MHz			
$I_C = I_c = 0$; V_{EB} = 0,5 V	C_e	<	8,0 pF
Transition frequency at f = 100 MHz			
I_C = 10 mA; V_{CE} = 20 V; T_{amb} = 25 °C	f_T	>	300 MHz
Noise figure at R_S = 1 kΩ			
I_C = 100 μA; V_{CE} = 5 V			
f = 10 Hz to 15,7 kHz; T_{amb} = 25 °C	F	<	5,0 dB

* Mounted on a ceramic substrate area = 2,5 cm^2; thickness = 0,7 mm.

h-parameters (common emitter)

I_C = 1 mA; V_{CE} = 10 V; f = 1 kHz; T_{amb} = 25 °C

Input impedance	h_{ie}		1 to 10 kΩ
Reverse voltage transfer ratio	h_{re}		0,5 to 8x10^{-4}
Small-signal current gain	h_{fe}		100 to 400
Output admittance	h_{oe}		1 to 40 μS

Switching times

Turn-on time (see Figs 2 and 3) when switched from

$-V_{BEoff}$ = 0,5 V to I_{Con} = 10 mA; I_{Bon} = 1 mA

Delay time	t_d	<	35 ns
Rise time	t_r	<	35 ns

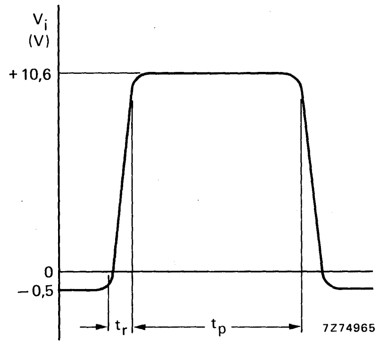


Fig. 2 Input waveform; t_r < 1 ns; t_p = 300 ns; δ = 0,02.

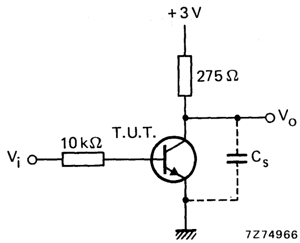


Fig. 3 Delay and rise time test circuit; total shunt capacitance of test jig and connectors C_s < 4 pF; scope impedance = 10 MΩ.

Turn-off time (see Figs 4 and 5)

I_{Con} = 10 mA; I_{Bon} = $-I_{Boff}$ = 1 mA

Storage time	t_s	<	200 ns
Fall time	t_f	<	50 ns

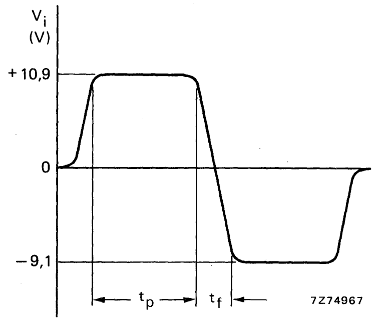


Fig. 4 Input waveform; t_f < 1 ns; 10 μs < t_p < 500 μs; δ = 0,02.

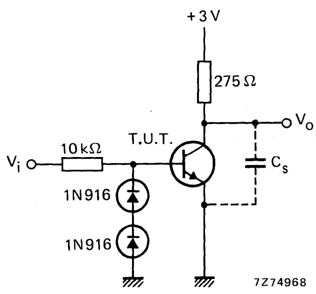


Fig. 5 Storage and fall time test circuit; total shunt capacitance of test jig and connectors C_s < 4 pF; scope impedance = 10 MΩ.

SILICON PLANAR EPITAXIAL TRANSISTOR

P-N-P transistor in a SOT-89 envelope primarily intended for high-speed, saturated switching applications for industrial service.

QUICK REFERENCE DATA

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	40	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	40	V
Collector current (d.c.)	$-I_C$	max.	200	mA
Total power dissipation at T_{amb} = 25 °C	P_{tot}	max.	1,0	W
Junction temperature	T_j	max.	150	°C
D.C. current gain $-I_C$ = 10 mA; $-V_{CE}$ = 1 V	h_{FE}	$>$ $<$	100 300	
Transition frequency at f = 100 MHz $-I_C$ = 10 mA; $-V_{CE}$ = 20 V	f_T	$>$	250	MHz
Storage time $-I_{Con}$ = 10 mA; $-I_{Bon}$ = I_{Boff} = 1 mA	t_s	$<$	225	ns

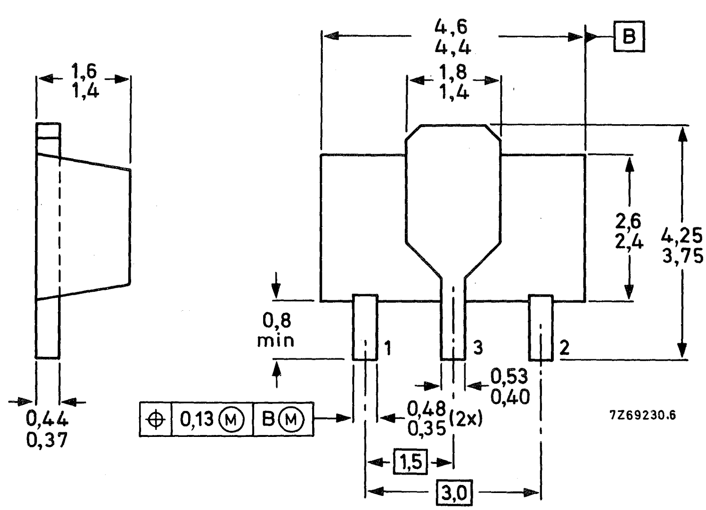
MECHANICAL DATA

Dimensions in mm

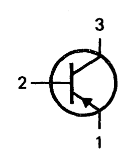
Fig. 1 SOT-89.

Marking code

P2A



BOTTOM VIEW



RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Collector-base voltage (open emitter)	$-V_{CBO}$	max.	40	V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	40	V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5	V
Collector current (d.c.)	$-I_C$	max.	200	mA
Total power dissipation at T_{amb} = 25 °C*	P_{tot}	max.	1,0	W
Storage temperature	T_{stg}		−55 to +150	°C
Junction temperature	T_j	max.	150	°C

THERMAL RESISTANCE

From junction to ambient in free air*	$R_{th\ j\text{-}a}$	=	125	K/W

CHARACTERISTICS

T_j = 25 °C unless otherwise specified

Currents at reverse biased emitter junction				
$-V_{CE}$ = 30 V; + V_{BE} = 3 V	$-I_{CEX}$	<	50	nA
	$+I_{BEX}$	<	50	nA
Saturation voltages				
$-I_C$ = 10 mA; $-I_B$ = 1 mA	$-V_{CEsat}$	<	250	mV
	$-V_{BEsat}$		650 to 850	mV
$-I_C$ = 50 mA; $-I_B$ = 5 mA	$-V_{CEsat}$	<	400	mV
	$-V_{BEsat}$	<	950	mV
D.C. current gain				
$-I_C$ = 0,1 mA; $-V_{CE}$ = 1 V	h_{FE}	>	60	
$-I_C$ = 1 mA; $-V_{CE}$ = 1 V	h_{FE}	>	80	
$-I_C$ = 10 mA; $-V_{CE}$ = 1 V	h_{FE}	>	100	
		<	300	
$-I_C$ = 50 mA; $-V_{CE}$ = 1 V	h_{FE}	>	60	
$-I_C$ = 100 mA; $-V_{CE}$ = 1 V	h_{FE}	>	30	
Collector capacitance at 100 kHz ⩽ f ⩽ 1 MHz				
$I_E = I_e = 0$; $-V_{CB}$ = 5 V	C_c	<	4,5	pF
Emitter capacitance at 100 kHz ⩽ f ⩽ 1 MHz				
$I_C = I_c = 0$; $-V_{EB}$ = 0,5 V	C_e	<	10	pF
Transition frequency at f = 100 MHz				
$-I_C$ = 10 mA; $-V_{CE}$ = 20 V; T_{amb} = 25 °C	f_T	>	250	MHz
Noise figure at R_S = 1 kΩ				
$-I_C$ = 100 μA; $-V_{CE}$ = 5 V				
f = 10 Hz to 15,7 kHz; T_{amb} = 25 °C	F	<	4,0	dB

* Mounted on a ceramic substrate area = 2,5 cm^2; thickness = 0,7 mm.

h-parameters (common emitter)

$-I_C = 1$ mA; $-V_{CE} = 10$ V; f = 1 kHz; $T_{amb} = 25$ °C

Input impedance	h_{ie}	2 to 12 kΩ
Reverse voltage transfer ratio	h_{re}	0,1 to 10×10^{-4}
Small-signal current gain	h_{fe}	100 to 400
Output admittance	h_{oe}	3 to 60 μS

Switching times

Turn-on time (see Figs 2 and 3) when switched from $+V_{BEoff} = 0{,}5$ V to $-I_{Con} = 10$ mA; $-I_{Bon} = 1$ mA

Delay time	t_d	<	35 ns
Rise time	t_r	<	35 ns

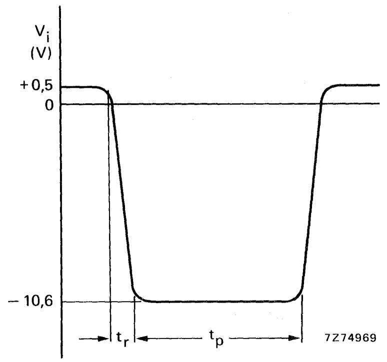


Fig. 2 Input waveform; $t_r < 1$ ns; $t_p = 300$ ns; $\delta = 0{,}02$.

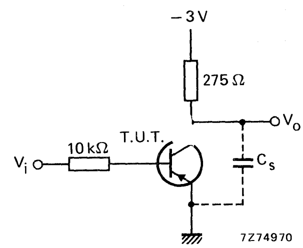


Fig. 3 Delay and rise time test circuit; total shunt capacitance of test jig and connectors $C_s < 4$ pF; scope impedance = 10 MΩ.

Turn-off time (see Figs 4 and 5)

$-I_{Con} = 10$ mA; $-I_{Bon} = I_{Boff} = 1$ mA

Storage time	t_s	<	225 ns
Fall time	t_f	<	75 ns

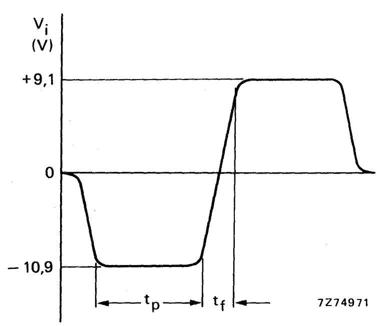


Fig. 4 Input waveform; $t_f < 1$ ns; 10 μs < t_p < 500 μs; $\delta = 0{,}02$.

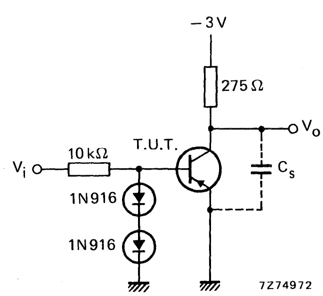
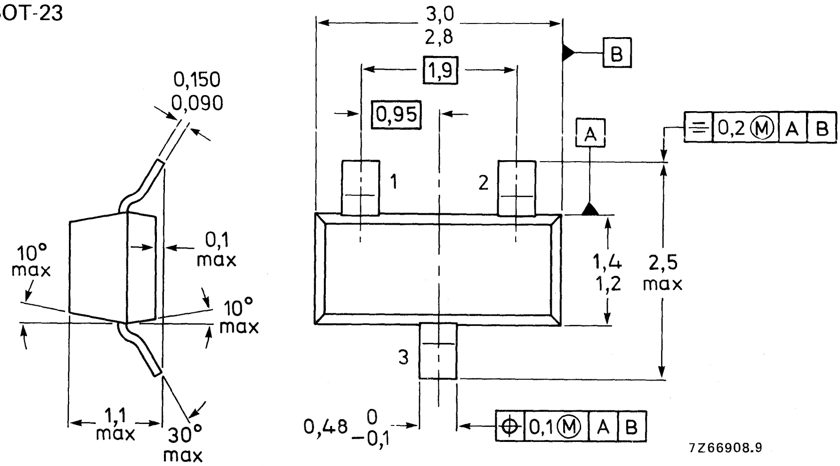


Fig. 5 Storage and fall time test circuit; total shunt capacitance of test jig and connectors $C_s < 4$ pF; scope impedance = 10 MΩ.

MECHANICAL DATA
(European projection)

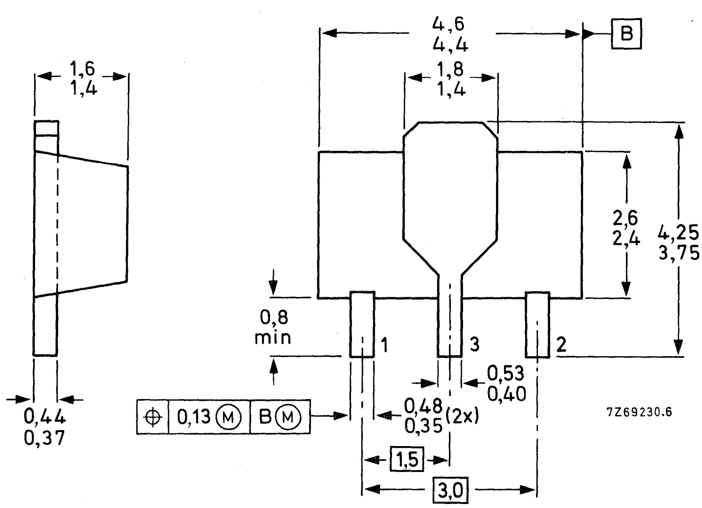
Dimensions in mm

SOT-23



TOP VIEW

SOT-89



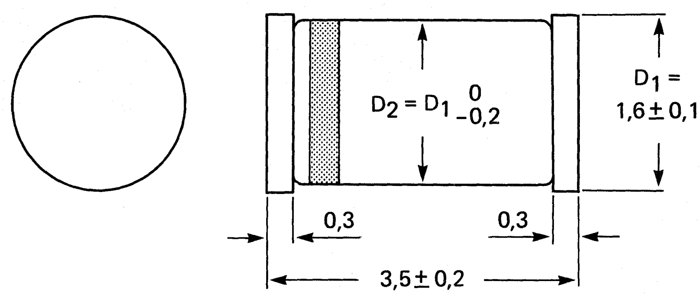
BOTTOM VIEW

MECHANICAL DATA

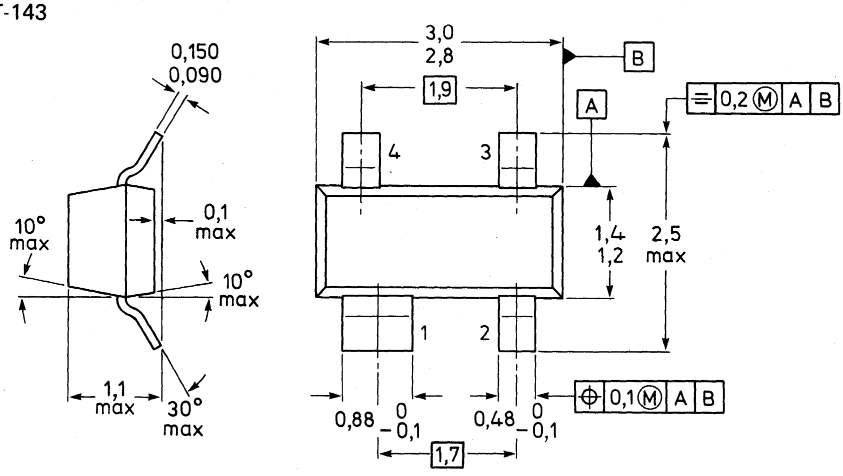
(European projection)

Dimensions in mm

SOD-80



SOT-143



TOP VIEW

INDEX OF TYPE NUMBERS

The inclusion of a type number in this publication does not necessarily imply its availability.

Mm = Microminiature semiconductors for hybrid circuits
SD = Small-signal diodes
Sp = Special diodes
T = Tuner diodes
Vrg = Voltage regulator diodes

* = series
FET = Field-effect transistors
Mm = Microminiature semiconductors for hybrid circuits
P = Low-frequency power transistors
Sm = Small-signal transistors
T = Tuner diodes

P = Low-frequency power transistors

P = Low-frequency power transistors

FET = Field-effect transistors
HVP = High-voltage power transistors
Mm = Microniature semiconductors for hybrid circuits
P = Low-frequency power transistors
Sm = Small-signal transistors
WBT = Wideband transistors

* = series
FET = Field-effect transistors
Mm = Microminiature semiconductors for hybrid circuits
RFP = R.F. power transistors and modules
RT = Tripler
Sm = Small-signal transistors
ThM = Thyristor modules
WBM = Wideband hybrid IC modules
WBT = Wideband transistors

* = series
FET = Field-effect transistors
RFP = R.F. power transistors and modules
ThM = Thyristor modules
WBM = Wideband hybrid IC modules

FET = Field-effect transistors
Mm = Microminiature semiconductors for hybrid circuits
PDT = Photodiodes or transistors
RFP = R.F. power transistors and modules
Sm = Small-signal transistors
Th = Thyristors

* = series
FET = Field-effect transistors
Mm = Microminiature semiconductors for hybrid circuits
Sm = Small-signal transistors
SP = Low-frequency switching power transistors
Th = Thyristors
Tri = Triacs

* = series
PM = Power MOS transistors
R = Rectifier diodes
SP = Low-frequency switching power transistors

* = series
LED = Light-emitting diodes
M = Microwave transistors
Mm = Microminiature semiconductors for hybrid circuits
Ph = Photoconductive devices
PhC = Photocouplers
R = Rectifier diodes
TS = Transient suppressor diodes
Vrf = Voltage reference diodes
Vrg = Voltage regulator diodes

INDEX

* = series
A = Accessories
I = Infrared devices
LED = Light-emitting diodes
M = Microwave transistors
PhC = Photocouplers
SEN = Sensors

FET = Field-effect transistors
I = Infrared devices
M = Microwave transistors
Mm = Microminiature semiconductors for hybrid circuits
P = Low-frequency power transistors
PhC = Photocouplers
R = Rectifier diodes
SD = Small-signal diodes
SEN = Sensors
Sm = Small-signal transistors
SP = Low-frequency switching power transistors
St = Rectifier stacks
WBM = Wideband hybrid IC modules

* = series
I = Infrared devices
M = Microwave transistors
P = Low-frequency power transistors
PhC = Photocouplers
R = Rectifier diodes
SD = Small-signal diodes
Vrf = Voltage reference diodes

A = Accessories
FET = Field-effect transistors
Ph = Photoconductive devices
PhC = Photocouplers
R = Rectifier diodes

RFP = R.F. power transistors and modules
SD = Small-signal diodes
Sm = Small-signal transistors
WBT = Wideband transistors

A = Accessories
FET = Field-effect transistors
Ph = Photoconductive devices
PhC = Photocouplers
Sm = Small-signal diodes

NOTES

NOTES

DATA HANDBOOK SYSTEM

DATA HANDBOOK SYSTEM

Our Data Handbook System comprises more than 60 books with specifications on electronic components, subassemblies and materials. It is made up of four series of handbooks:

ELECTRON TUBES	BLUE
SEMICONDUCTORS	RED
INTEGRATED CIRCUITS	PURPLE
COMPONENTS AND MATERIALS	GREEN

The contents of each series are listed on pages iv to vii.

The data handbooks contain all pertinent data available at the time of publication, and each is revised and reissued periodically.

When ratings or specifications differ from those published in the preceding edition they are indicated with arrows in the page margin. Where application information is given it is advisory and does not form part of the product specification.

Condensed data on the preferred products of Philips Electronic Components and Materials Division is given in our Preferred Type Range catalogue (issued annually).

Information on current Data Handbooks and on how to obtain a subscription for future issues is available from any of the Organizations listed on the back cover.
Product specialists are at your service and enquiries will be answered promptly.

ELECTRON TUBES (BLUE SERIES)

The blue series of data handbooks comprises:

T1	**Tubes for r.f. heating**
T2a	**Transmitting tubes for communications, glass types**
T2b	**Transmitting tubes for communications, ceramic types**
T3	**Klystrons**
T4	**Magnetrons for microwave heating**
T5	**Cathode-ray tubes** Instrument tubes, monitor and display tubes, C.R. tubes for special applications
T6	**Geiger-Müller tubes**
T8	**Colour display systems** Colour TV picture tubes, colour data graphic display tube assemblies, deflection units
T9	**Photo and electron multipliers**
T10	**Plumbicon camera tubes and accessories**
T11	**Microwave semiconductors and components**
T12	**Vidicon and Newvicon camera tubes**
T13	**Image intensifiers and infrared detectors**
T15	**Dry reed switches**
T16	**Monochrome tubes and deflection units** Black and white TV picture tubes, monochrome data graphic display tubes, deflection units

SEMICONDUCTORS (RED SERIES)

The red series of data handbooks comprises:

S1	**Diodes** Small-signal silicon diodes, voltage regulator diodes (< 1,5 W), voltage reference diodes, tuner diodes, rectifier diodes
S2a	**Power diodes**
S2b	**Thyristors and triacs**
S3	**Small-signal transistors**
S4a	**Low-frequency power transistors and hybrid modules**
S4b	**High-voltage and switching power transistors**
S5	**Field-effect transistors**
S6	**R.F. power transistors and modules**
S7	**Surface mounted semiconductors**
S8a	**Light-emitting diodes**
S8b	**Devices for optoelectronics** Optocouplers, photosensitive diodes and transistors, infrared light-emitting diodes and infrared sensitive devices, laser and fibre-optic components
S9	**Power MOS transistors**
S10	**Wideband transistors and wideband hybrid IC modules**
S11	**Microwave transistors**
S12	**Surface acoustic wave devices**
S13	**Semiconductor sensors**
S14	**Liquid Crystal Displays**

INTEGRATED CIRCUITS (PURPLE SERIES)

The purple series of handbooks comprises:

IC01	**Radio, audio and associated systems** Bipolar, MOS	published 1986
IC02a/b	**Video and associated systems** Bipolar, MOS	published 1986
IC03	**Integrated circuits for telephony** Bipolar, MOS	published 1986
IC04	**HE4000B logic family** CMOS	published 1986
IC05N	**HE4000B logic family — uncased ICs** CMOS	published 1984
IC06N	**High-speed CMOS; PC74HC/HCT/HCU** Logic family	published 1986
IC08	**ECL 10K and 100K logic families**	published 1986
IC09N	**TTL logic series**	published 1986
IC10	**Memories** MOS, TTL, ECL	new issue 1987
IC11N	**Linear LSI**	published 1985
Supplement to IC11N	**Linear LSI**	published 1986
IC12	**I^2C-bus compatible ICs**	not yet issued
IC13	**Semi-custom** Programmable Logic Devices (PLD)	new issue 1987
IC14	**Microcontrollers and peripherals** Bipolar, MOS	new issue 1987
IC15	**FAST TTL logic series**	published 1986
IC16	**CMOS integrated circuits for clocks and watches**	published 1986
IC17	**Integrated Services Digital Networks (ISDN)**	not yet issued
IC18	**Microprocessors and peripherals**	new issue 1987

COMPONENTS AND MATERIALS (GREEN SERIES)

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